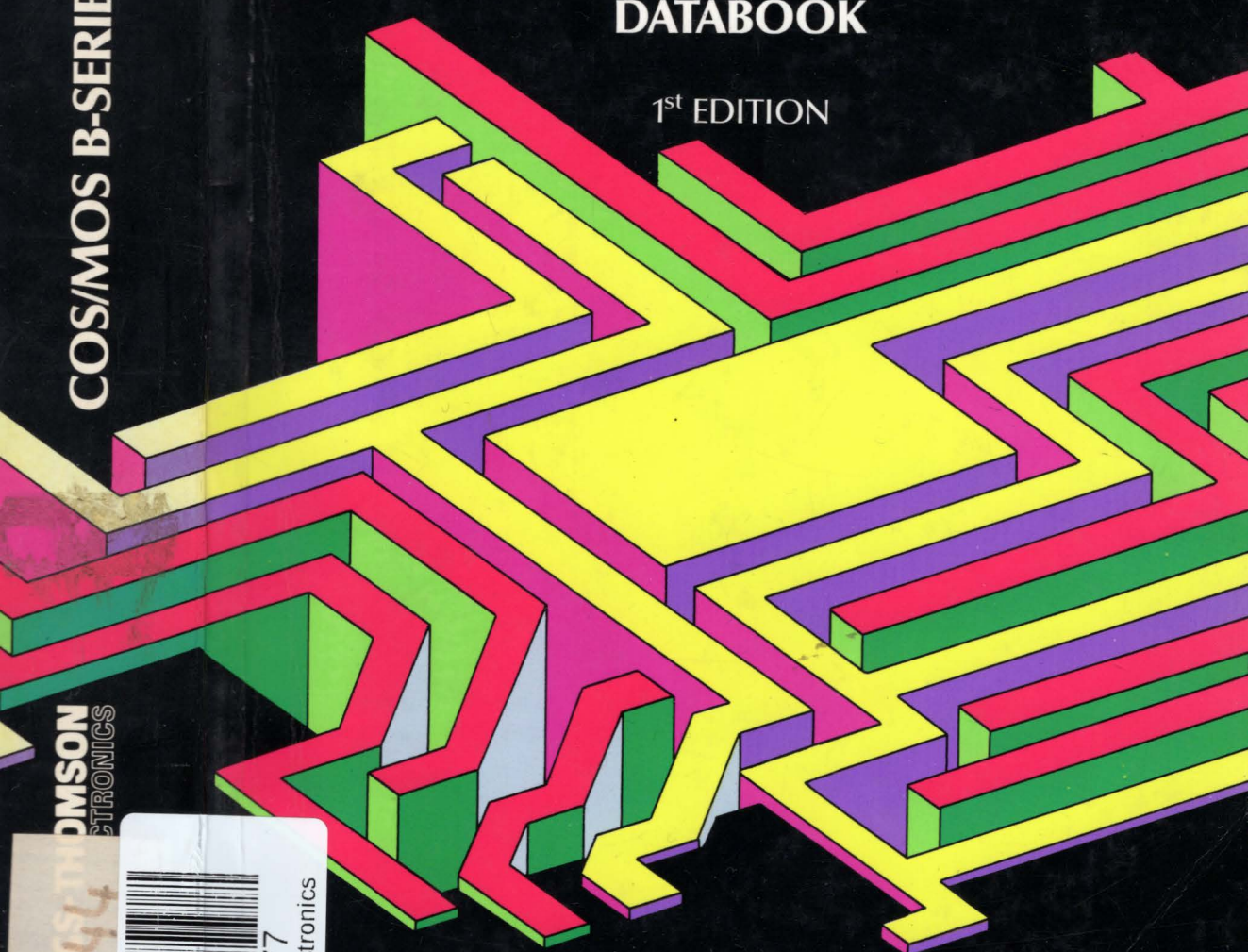


COS/MOS B-SERIES DEVICES

COS/MOS B-SERIES DEVICES

DATABOOK

1st EDITION



SGS-THOMSON
MICROELECTRONICS

53144



000477
RYSTON Electronics



SGS-THOMSON
MICROELECTRONICS

3144

COS/MOS B-SERIES DEVICES

DATABOOK

1st EDITION

SEPTEMBER 1991

477

USE IN LIFE SUPPORT DEVICES OR SYSTEMS MUST BE EXPRESSLY AUTHORIZED

SGS-THOMSON PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF SGS-THOMSON Microelectronics. As used herein:

1. Life support devices or systems are those which (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided with the product, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can reasonably be expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

TABLE OF CONTENTS

INTRODUCTION	Page	4
<hr/>		
ALPHANUMERICAL INDEX		5
<hr/>		
SELECTION GUIDE		9
<hr/>		
GENERAL AND APPLICATION INFORMATION		13
<hr/>		
MILITARY / CECC PRODUCTS		27
<hr/>		
RADIATION HARDENED PRODUCTS		37
<hr/>		
RELIABILITY REPORT		47
<hr/>		
DATASHEETS		61
<hr/>		
PACKAGES		849

INTRODUCTION

This databook contains datasheets on the SGS-THOMSON range of CMOS B-series integrated circuits.

The information on each product, in accordance with EIA/JEDEC specifications, has been specially presented in order that the performance of the product can be readily evaluated within any required equipment design.

The two sections, Military/CECC and Radiation Hardened products, are included for more stringent device requirements such as Military, Space, Biomedical and other high reliability applications.

New developments in packaging include the PLCC package; all the surface out-line packages (SO) are made to JEDEC standards.

In addition, general considerations that should be taken into account in the operation and application of CMOS B-series integrated circuits are described. Selection guides are included to simplify the task of choosing the best combination of circuits a for system.

The databook also contains the results of the reliability studies made by SGS-THOMSON on its CMOS B-series.

ALPHANUMERICAL INDEX

Type Number	Function	Package DIP	Page Number
HCC/HCF 4000B	Dual 3-Input NOR Gate Plus Inverter	14	63
HCC/HCF 4001B	Quad 2-Input NOR Gate	14	63
HCC/HCF 4002B	Dual 4-Input NOR Gate	14	63
HCC/HCF 4006B	18-Stage Static Shift Register	14	71
HCC/HCF 4007UB	Dual Complementary Pair Plus Inverter	14	77
HCC/HCF 4008B	4 Bit Full Adder	16	87
HCC/HCF 4009UB	Hex Buffer/Converters Inverting	16	95
HCC/HCF 4010B	Hex Buffer/Converters non Inverting	16	95
HCC/HCF 4011B	Quad 2-Input NAND Gate	14	103
HCC/HCF 4012B	Dual 4-Input NAND Gate	14	103
HCC/HCF 4013B	Dual D Flip-Flop	14	111
HCC/HCF 4014B	8-Stage Static Synchronous Shift Register	16	117
HCC/HCF 4015B	Dual 4-Stage Static Shift Register	16	125
HCC/HCF 4016B	Quad Bilateral Switch	14	133
HCC/HCF 4017B	Decade Counter/Divider	16	143
HCC/HCF 4018B	Presettable Divide-by-"N" Counter	16	151
HCC/HCF 4019B	Quad AND/OR Select Gate	16	159
HCC/HCF 4020B	14-Stage Binary/Ripple Counter	16	167
HCC/HCF 4021B	8-Stage Static Shift Register	16	117
HCC/HCF 4022B	Divide-by-8 Counter/Divider	16	143
HCC/HCF 4023B	Triple 3-Input NAND Gate	14	103
HCC/HCF 4024B	7-Stage Binary/Ripple Counter	14	167
HCC/HCF 4025B	Triple 3-Input NOR Gate	14	63
HCC/HCF 4026B	Decade Counter/Divider 7-Segment Display Driver	16	173
HCC/HCF 4027B	Dual J-K Master-Slave Flip-Flop	16	183
HCC/HCF 4028B	BCD-to-Decimal Decoder	16	191
HCC/HCF 4029B	Presettable Up/Down Counter	16	201
HCC/HCF 4030B	Quad Exclusive OR Gate	14	209
HCC/HCF 4031B	64-Stage Static Shift Register	16	217
HCC/HCF 4032B	Triple Serial Adder	16	225
HCC/HCF 4033B	Decade Counter/Divider 7-Segment Display Driver	16	173
HCC/HCF 4034B	8-Stage Static Bidirectional Bus Register	24	233
HCC/HCF 4035B	4-Stage Parallel I/O Shift Register	16	245
HCC/HCF 4038B	Triple Serial Adder	16	225
HCC/HCF 4040B	12-Stage Binary/Ripple Counter	14	167
HCC/HCF 4041UB	Quad True/Complement Buffer	14	255
HCC/HCF 4042B	Quad Clocked D Latch	16	263
HCC/HCF 4043B	Quad 3-State NOR R/S Latch	16	271
HCC/HCF 4044B	Quad 3-State NAND R/S Latch	16	271
HCC/HCF 4045B	21-Stage Counter	16	279
HCC/HCF 4046B	Micropower Phase Locked Loop	16	285
HCC/HCF 4047B	Monostable/Astable Multivibrator	14	295
HCC/HCF 4048B	Multifunction Expandable 8-Input Gate	16	305

ALPHANUMERICAL INDEX

Type Number	Function	Package DIP	Page Number
HCC/HCF 4049UB	Hex Inverting Buffer/Converter	16	313
HCC/HCF 4050B	Hex Non Inverting Buffer/Converter	16	313
HCC/HCF 4051B	Single 8-Channel Analog Multiplexer/Demultiplexer	16	321
HCC/HCF 4052B	Different. 4-Channel Analog Multiplexer/Demultiplexer	16	321
HCC/HCF 4053B	Triple 2-Channel Analog Multiplexer/Demultiplexer	16	321
HCC/HCF 4054B	4-Segment Display Driver	16	333
HCC/HCF 4055B	BCD to 7-Segment Decoder/Driver	16	333
HCC/HCF 4056B	BCD to 7-Segment Decoder/Driver	16	333
HCC/HCF 4060B	14-Stage Counter/Divider AND Oscillator	16	343
HCC/HCF 4063B	4-Bit Magnitude Comparator	16	351
HCC/HCF 4066B	Quad Bilateral Switch	24	359
HCC/HCF 4067B	Single 16-Channel Analog Multiplexer/Demultiplexer	24	365
HCC/HCF 4068B	8-Input NAND/AND Gate	14	377
HCC/HCF 4069UB	Hex Inverter	14	383
HCC/HCF 4070B	Quad Exclusive-Or Gate	14	391
HCC/HCF 4071B	Quad 2-Input OR Gate	14	397
HCC/HCF 4072B	Dual 4-Input OR Gate	14	397
HCC/HCF 4073B	Triple 3-Input AND Gate	14	403
HCC/HCF 4075B	Triple 3-Input OR Gate	14	397
HCC/HCF 4076B	4-Bit D-Type Register	16	409
HCC/HCF 4077B	Quad Exclusive-NOR Gate	14	391
HCC/HCF 4078B	8-Input NOR/OR Gate	14	417
HCC/HCF 4081B	Quad 2-Input AND Gate	14	403
HCC/HCF 4082B	Dual 4-Input AND Gate	14	403
HCC/HCF 4085B	Dual 2-Wide 2-Input AND-OR-Inverter Gate	14	423
HCC/HCF 4086B	Expand 4-Wide 2-Input AND-OR-Inverter Gate	14	431
HCC/HCF 4089B	Binary Rate Multiplexer	16	439
HCC/HCF 4093B	Quad 2-Input NAND Schmitt Trigger	14	449
HCC/HCF 4094B	8-Stage Shift-AND-Store Bus Register	16	457
HCC/HCF 4095B	Gated J-K Master-Slave Flip-Flop	14	467
HCC/HCF 4096B	Gated J-K Master-Slave Flip-Flop	14	467
HCC/HCF 4097B	Different. 8-Channel Analog Multiplexer/Demultiplexer	24	365
HCC/HCF 4098B	Dual Monostable Multivibrator	16	475
HCC/HCF 4099B	8-Bit Addressable Latch	16	485
HCC/HCF 4502B	Strobed Hex Inverter/Buffer	16	495
HCC/HCF 4503B	Hex Buffer (3-State non-Inverter)	16	501
HCC/HCF 4504B	Hex TTL or CMOS to CMOS Level Shifter	16	509
HCC/HCF 4508B	Dual 4-Bit Latch (3-State Outputs)	24	511
HCC/HCF 4510B	Presetable 4-Bit BCD Up/Down Counter	16	521
HCC/HCF 4511B	BCD to 7 Segment Latch-Decoder/Driver	16	531
HCC/HCF 4512B	8-Channel Data Selector With 3-State Output	16	543
HCC/HCF 4514B	4-Bit Latch/4-to-16 Line Decoder (Out. High)	24	551
HCC/HCF 4515B	4-Bit Latch/4-to-16 Line Decoder (Out. Low)	24	551

ALPHANUMERICAL INDEX

Type Number	Function	Package DIP	Page Number
HCC/DCF 4516B	Presetable 4-Bit Binary Up/Down Counter	16	521
HCC/DCF 4517B	Dual 64-Stage Static Shift Register	16	559
HCC/DCF 4518B	Dual BCD Up Counter	16	567
HCC/DCF 4519B	4-Bit AND/OR Selector	16	577
HCC/DCF 4520B	Dual Binary Up Counter	16	567
HCC/DCF 4521B	24-Stage Frequency Divider	16 ^e	579
HCC/DCF 4522B	Programmable BCD Divider-by-N Counter	16 ^e	581
HCC/DCF 4527B	BCD Rate Multiplier	16 ^e	583
HCC/DCF 4529B	Dual 4-Channel or Single 8-Channel Analog Data Selector	16	593
HCC/DCF 4532B	8-Input Priority Encoder	16	599
HCC/DCF 4536B	Programmable Timer	16 ^e	609
HCC/DCF 4538B	Dual Precision Monostable Multivibrator	16	623
HCC/DCF 4541B	Programmable Timer	14	633
HCC/DCF 4543B	BCD-to-7 Segment Latch/Decoder/Driver	16	639
HCC/DCF 4555B	Dual 1-of-4 Decoder/Demultiplexer (Out. High)	16	647
HCC/DCF 4556B	Dual 1-of-4 Decoder/Demultiplexer (Out. Low)	16	647
HCC/DCF 4560B	NBCD Adder	16 ^a	657
HCC/DCF 4566B	Industrial Time-Base Generator	16 ^v	659
HCC/DCF 4572B	Hex Gate	16	661
HCC/DCF 4585B	4-Bit Magnitude Comparator	16	663
HCC/DCF 4724B	8-Bit Addressable Latch	16 ^r	671
HCC/DCF 40100B	32-Stage Static Left/Right Shift Register	16 ^v	681
HCC/DCF 40101B	9-Bit Parity Generator/Checker	14	689
HCC/DCF 40102B	Presetable 2-Decade BCD Down Counter	16	695
HCC/DCF 40103B	Presetable 8-Bit Binary Down Counter	16	695
HCC/DCF 40104B	4-Bit Bidirectional Universal Shift Register	16 ^b	705
HCC/DCF 40105B	4-Bit x 16 Word	14	713
HCC/DCF 40106B	Hex Schmitt Trigger	14	721
HCC/DCF 40107B	Dual 2-Input NAND Buffer/Driver	8	729
HCC/DCF 40108B	4x4 Multiport Register	24	739
HCC/DCF 40109B	Quad Low-to-High Voltage Level Shifter	16	749
HCC/DCF 40110B	Decade Up Down Counter/Decoder/Latch/Driver	16 ^e	757
HCC/DCF 40147B	10-Line to 4-Line BCD Priority Encoder	16	765
HCC/DCF 40160B	Decade Counter/Asynchronous Clear	16	773
HCC/DCF 40161B	Binary Counter/Asynchronous Clear	16	773
HCC/DCF 40162B	Decade Counter/Synchronous Clear	16	773
HCC/DCF 40163B	Binary Counter/Synchronous Clear	16	773
HCC/DCF 40174B	Hex "D"	16	783
HCC/DCF 40181B	4-Bit Arithmetic Logic Unit	24	791
HCC/DCF 40182B	Look-Ahead Carry Generator	16	799
HCC/DCF 40192B	Presetable 4-Bit BCD Up/Down Counter	16	807
HCC/DCF 40193B	Presetable 4-Bit Binary Up/Down Counter	16	807
HCC/DCF 40194B	4-Bit Bidirectional Universal Shift Register	16	705
HCC/DCF 40208B	4x4 Multiport Register	24	817

ALPHANUMERICAL INDEX

Type Number	Function	Package DIP	Page Number
HCC/HCF 40257B	Quad 2-Line-to-1-Line Data Selector/Multiplexer	16	827
M22100	4x4 Cross Point Switch with Control Memory	16	833
M22101	4x4x2 Cross Point Switches with Control Memory	24	843
M22102	4x4x2 Cross Point Switches with Control Memory	24	843

SELECTION GUIDE

HCC/HCF 4000B/4500B 40100B STANDARD SERIES AND CROSSPOINT SWITCHES

Function		Standard Code
GATE BUFFER	NAND	4011B, 4012B, 4023B, 4068B, 40107B
	NOR	4000B
	AND	4068B, 4073B, 4081B, 4082B
	OR	4071B, 4072B, 4075B, 4078B
	INVERTER	4069UB, 4502B
	BUFFER	4007UB, 4009UB, 4010B, 4041UB, 4049UB, 4050B, 4502B, 4503B, 40107B
	MULTIFUNCTION	4019B, 4030B, 4048B, 4070B, 4077B, 4085B, 4086B, 4572UB, 4504B
	SCHMITT TRIGGER	4093B, 40106B
FLIP-FLOP	J-K FLIP-FLOP	4027B, 4095B, 4096B
	D FLIP-FLOP	4013B, 4076B, 40174B
INTERFACE CIRCUIT		4009UB, 4010B, 4504B, 40109B
LATCH		4042B, 4043B, 4044B, 4099B, 4508B
MULTIVIBRATOR		4047B, 4098B, 4538B
DECODER		4028B, 4514B, 4515B, 4555B, 4556B
ENCODER		4532B, 40147B
DISPLAY DRIVER		4054B, 4055B, 4056B, 4511B, 4543B
		WITH COUNTER
REGISTER	SHIFT STATIC	4006B, 4014B, 4015B, 4021B, 4031B, 4034B, 4035B, 4094B, 4517B, 40100B, 40104B, 40194B
	STORAGE	4076B, 4099B, 40108B, 40208B
	FIFO	40105B
COUNTER	SYNCHRONOUS	4017B, 4018B, 4022B, 4029B, 4510B, 4516B, 4518B, 4520B, 4521B, 4522B, 40102B, 40103B, 40160B, 40161B, 40162B, 40163B, 40192B, 40193B
	BINARY RIPPLE	4020B, 4024B, 4040B, 4060B
	CLOCK TIMER	4045B, 4536B, 4541B, 4566B
MULTIPLEXER/ DEMULTIPLEXER	ANALOGIC DIGITAL	4016B, 4019B, 4051B, 4052B, 4053B, 4066B, 4067B, 4097B, 4555B, 4556B
	DATA SELECTOR	4512B, 4529B, 40257B, 4519B
ARITHMETIC CIRCUIT	ADDER	4008B, 4032B, 4038B, 4560B
	COMPARATOR	4030B, 4063B, 4070B, 4077B, 4585B, 40101B
	ALU / MULTIPLEXER	4089B, 4527B, 40181B, 40182B
PHASE LOCKED LOOP		4046B
CROSSPOINT SWITCH	4x4	22100
	4x4x2	22101, 22012

GENERAL AND APPLICATION INFORMATION

THE PRODUCT FEATURES

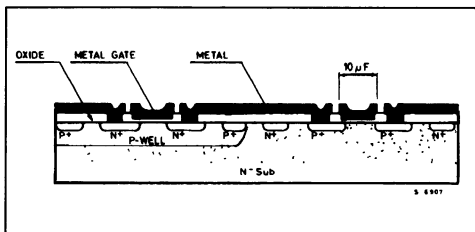
SGS-THOMSON's 4000B family of metal gate CMOS monolithic integrated circuits provides the design engineer with a wide range of products which approach the ideal in performance.

The combination of low power dissipation, flexible power-supply design, high noise immunity and fan-out capability have made this logic family extremely popular.

These products are mainly used in telecommunication and consumer/commodity fields and high reliability applications such as space and biomedical use.

SGS-THOMSON CMOS 4000B family is backed up by one of the most extensive product ranges in the industry, a cost effectiveness together with high-reliability and high quality thus offering the user the best solution to a greater number of applications.

CMOS Metal Gate



THE PRODUCT TECHNOLOGY

Although the CMOS 4000B is a mature product family, SGS-THOMSON continuously introduces improvements in the process, according to the present "state of the art".

Ion implantation gives precise control of channel doping allowing a much tighter distribution of device parameters and better reproducibility of the process.

The entire process is tracked using an on-line computer system. Moreover, in line with SGS-THOMSON quality control philosophy, particular attention is paid to upgrading production facilities. All the above factors lead to improvements in reliability, controllability, repeatability or, in one word, quality.

THE PRODUCT INFORMATION

The SGS-THOMSON CMOS HCC/HCF 4000B series meets the industry standardized specifications co-ordinated by EIA/JEDEC Solid State Products Council.

The official JEDEC specifications for static parameters are primarily applicable to gates, inverters, high current (inverting) drivers and devices with Medium Scale Integration.

Special types such as analog switches, multiplexers and multivibrators do not have the same input-output standards as the B series specifications but are still given with a B suffix because they satisfy the remaining JEDEC specifications.

SGS-THOMSON HCC/HCF 4000B types have the following Absolute Maximum Ratings:

Symbol	Description	Value	Unit
V _{DD}	Supply Voltage: HCC HCF (1)	-0.5 to 20 -0.5 to 18	V V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature: HCC types HCF types	-55 to + 125 -40 to + 85	°C °C
T _{stg}	Storage Temperature	-65 to + 150	°C

1) During factory testing, the HCF devices are measured applying the same values of supply voltage as for HCC types. Moreover the HCF limits for quiescent current (I_L) and input leakage current (I_{IH}, I_{IL}) are as for the HCC limits.

The Recommended Operating Conditions are specified as follows:

Symbol	Parameter	Value	Unit
V _{DD}	Supply voltage: HCC HCF (1)	3 to 18 3 to 15	V V
V _I	Input voltage	0 to V _{DD}	V
T _{op}	Operating temperature: HCC types HCF types	-55 to + 125 -40 to + 85	°C °C

1) During factory testing, the HCF devices are measured applying the same values of supply voltage as for HCC types. Moreover the HCF limits for quiescent current (I_L) and input leakage current (I_{IH}, I_{IL}) are as for the HCC limits.

If these ratings are compared with the corresponding JEDEC values shown in table II and III it can be seen that the SGS-THOMSON HCC/HCF 4000B devices have much better limits than those of the JEDEC specifications. The static electrical characteristics of the HCC/HCF 4000B series, excluding special devices such as analog switches, multiplexers, drivers, etc. are shown in table I.

The SGS-THOMSON HCC/HCF 4000B family has the quiescent leakage current (I_L), specified at 5, 10, 15, 20 V and the other static electrical characteristics at 5, 10, 15 V for both extended and intermediate temperature ranges.

HCC/HCF 4000B Series Features

The principal features of the HCC/HCF 4000B series are as follows:

- Operating range of **HCC** 3-18V; **HCF** 3-15V
- Rationalised range of quiescent leakage current (I_L) specifications corresponding to gate, buffer and flip-flop, and Medium Scale Integration products.
- Maximum input leakage current (I_{IH}, I_{IL}) of ± 1 µA at V_{DD}= 18V for **HCC**, 15V for **HCF** with V_I= 0 to 18V for **HCC**, 0 to 15V for **HCF**, over the full temperature range.
- Input and output logic levels completely independent of temperature.
- Input voltage levels which define a very high DC noise immunity (45% V_{DD} typical).
- Noise margins of 1.0V min. at 5V V_{DD}
2.0V min. at 10V V_{DD}
2.5V min. at 15V V_{DD}

- Low (400 Ω typical) and constant output impedance in both logical states giving fixed and equal output transition times.
- Output current capable of driving
 - a) two low power TTL loads
 - b) one low power Schottky TTL load
 - c) two HLL loads over the rated temperature range.
- Output current and input threshold independent of the number of inputs parallel together.
- Square transfer voltage characteristics.

General COS/MOS Characteristics

The main advantages offered by COS/MOS devices over corresponding bipolar devices (DTL, LPS, TTL, ECL, HLL) are:

- Very low quiescent power dissipation (typically 10 nW/gate, 10 µW/MSI)
- Wide operating voltage range (3 to 18V for **HCC**; 3-15V for **HCF**)
- High input impedance (typically 10¹² Ω)
- High DC noise immunity (typically 45% of supply voltage).

This digital family however has slower switching speeds than most bipolar families.

For example the typical propagation times for COS/MOS and other logic families are:

Propagation Delay Time (ns)	COS/MOS	ECL	LPS	TTL	DTL	HLL
	35	2	5	10	30	110

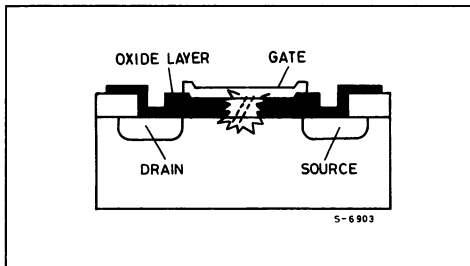
Moreover, due to the high input impedance of the MOS gates, COS/MOS devices require greater care in handling.

The normal gate oxide thickness is 800 to 1000Å with a corresponding breakdown voltage between gate and substrate of 80 to 90V.

The electrostatic potential of the human body is much higher than this range, reaching 12kV with a discharge capacity of approximately 100 pF.

Electronic components have to be protected from the hazard of static electricity, from the manufacturing stage down to where they are utilized. MOS devices are typically voltage and field sensitive; the thin oxide layers can be destroyed by the electric field.

Fig. A



This happens mostly because a charged conductor, typically a person, is rapidly discharged through the device.

There will be no net charge on any portion of the MOS structure; when the induced high field exceeds the breakdown voltage of the MOS capacitor structure we may have a self-healing break-down, degradation or catastrophic failure.

The failure hazard is not limited to the gate region but it could occur wherever two conductive areas are separated by a thin insulator.

We have envisaged two sets of precautions: input protection networks and static discharge control (handling).

The HCC/HCF 4000B devices use an improved protection network over that used in the 4000A series. The level of protection for the 4000B products has been raised to 4 kV, the previous solution for the 4000A products protected the gate oxide against electrostatic discharges only up to approximately 1 kV. The following figures show the difference between the two input protection networks for a basic inverter:

Fig. B

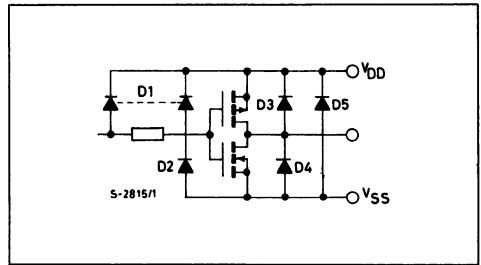
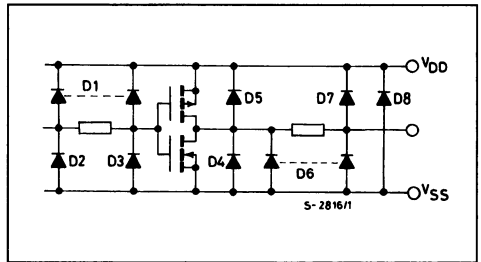
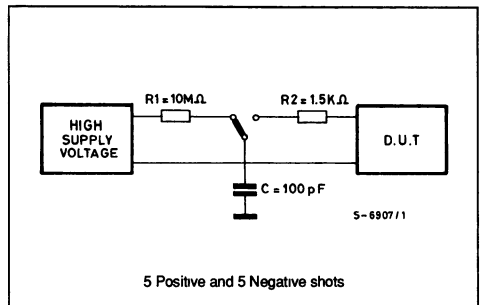


Fig. C



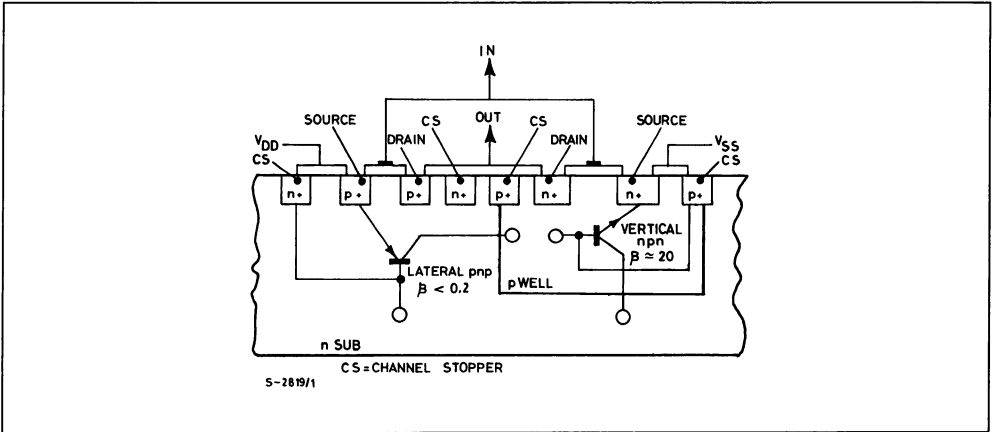
The protection capability has been verified with the following discharge set as show in figure below.

Measurement to the MIL-STD 883C-3015



In COS/MOS as in Linear Integrated Circuits a "latch-up" phenomenon may appear. This is caused by an electrical pulse which, acting on an SCR structure of parasitic bipolar transistors inside COS/MOS devices (shown in fig. D), produces a low resistance path between supply voltage and ground that remains after the pulse has ceased leading rapidly to device destruction.

Fig. D



This phenomenon will occur either when V_{DD} is more than the maximum rating and approaches the breakdown voltage of the SCR structure or when any of the following conditions are verified:

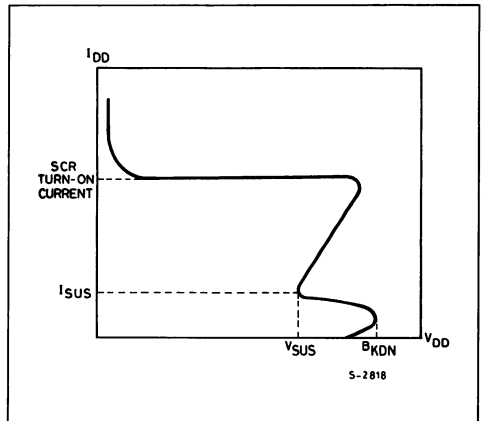
- a) the product of the gains of the two parasitic transistors is greater than or equal to unity;
- b) the base-emitter junction of both transistors is forward biased;
- c) supply voltage and input circuits are able to deliver a current equal to the holding current of the SCR (fig. E).

In particular, condition (b) may be caused by:

- 1) voltages induced through the oxide by base metallization;
- 2) lateral voltage drops between substrate and P-well due to photo-current generated by radiation. These drops can forward bias the gate-cathode junction of the parasitic SCR.

This effect is particularly significant in buffers which are devices most subject to latch-up due to the

Fig. E



combination of large geometry and low silicon resistivity. For these reasons voltage transient or large output current surges occurring during operation near the maximum rating should be avoided.

The B series devices are much better protected against latch-up than the A series because of their higher typical breakdown voltage:

Characteristics	A series	B series
V_{BR}	17 V	25 V
V_{SUS}	15 V	22 V
I_{SUS}	10 to 40 mA	50 to 100 mA

B Series Dynamic Switching Parameters

The dynamic electrical characteristics are specified at $T_{amb}= 25^{\circ}C$ under the following conditions:

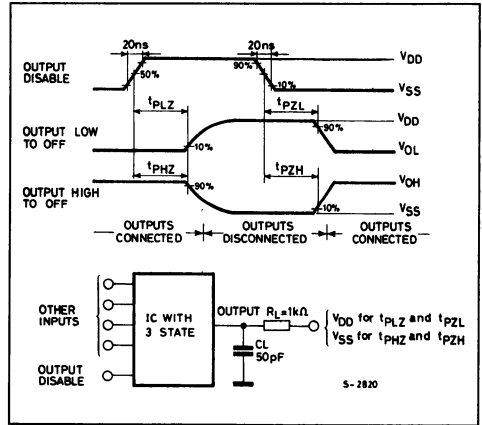
- load capacitance (C_L) of 50 pF and load resistance (R_L) of 200 k Ω ;
- input pulse amplitude equal to supply voltage (V_{DD});
- input rise and fall times of 20 ns;
- propagation delay times measured from 50% of the input voltage to the 50% point of the output voltage;
- transition times measured from 10% to 90% of the supply voltage (V_{DD}).

In some devices other time parameters are also specified:

- a) Set up time
- b) Hold time
- c) Removal time
- d) Tri-state disable delay times.

The figures (F and G) show the meaning of these parameters

Fig. F



The corresponding values of suffix B types are:

$$V_{IL} = 30\% V_{DD} \quad \text{for } V_{DD} = 5V \text{ and } 10V$$

$$V_{IH} = 70\% V_{DD}$$

and

$$V_{IL} = 27\% V_{DD}$$

$$V_{IH} = 73\% V_{DD} \quad \text{for } V_{DD} = 15V$$

The other main differences between B and UB gates are summarized on the page 20.

If B and UB gates are presented with slow transition time signals the behaviour of the two types differs. In fact, because of high AC gain of B devices (obtained with the two extra inverters) the outputs tend to develop a few cycles of oscillation between V_{DD} and V_{SS} when input rise or fall time is more than 1 ms at $V_{DD} = 5V$ and AC noise is reduced to 2-3 mV within the B device bandwidth.

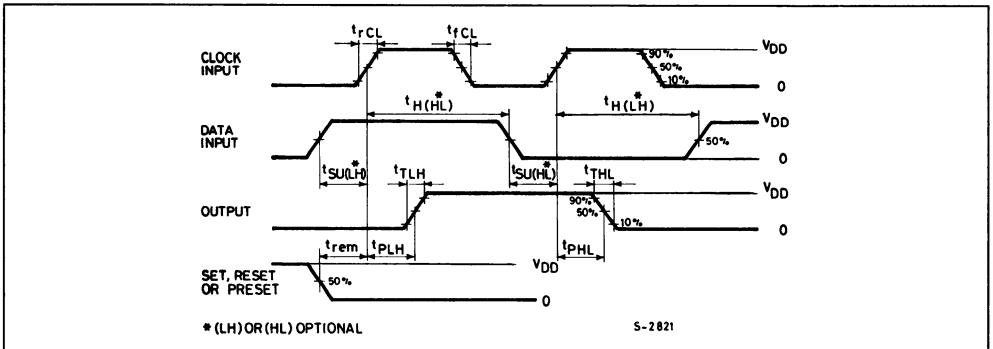
The unbuffered gates (which have less gain) tend not to oscillate with the same input ramp unless a noise voltage of 200 to 300 mV is present within the device bandwidth.

Comparison between B and UB devices

The **HCC/HCF 4000B** family also includes suffix UB products that only meet some of the B series electrical specifications.

These have logic outputs that are not buffered, and V_{IL} and V_{IH} that are specified at 20% V_{DD} and 80% V_{DD} respectively for $V_{DD} = 5V$ and 10V and 17% V_{DD} and 83% V_{DD} respectively for $V_{DD} = 15V$.

Fig. G



Characteristics	Buffered	Unbuffered
Typical Output Impedance	Constant: 400 Ω (typ) at $V_{DD}=5V$	Variable: Dependent on number of inputs paralleled together
Voltage Transfer Characteristic	Square and independent of the number of inputs tied together	Rounded (as A serial) and shifted with different number of inputs paralleled together
Propagation Delay	Moderate: 150 ns at $V_{DD}=5V$ 65 ns at $V_{DD}=10V$ 50 ns at $V_{DD}=15V$	Fast: 60 ns at $V_{DD}=5V$ 30 ns at $V_{DD}=10V$ 25 ns at $V_{DD}=15V$
AC Gain	High and constant: $\cong 68$ dB	Low and dependent on supply voltage: 28 dB at $V_{DD}=5V$ 23 dB at $V_{DD}=10V$ 18 dB at $V_{DD}=15V$
AC Band Width	Low: 230 kHz at $V_{DD}=5V$ 280 kHz at $V_{DD}=10V$ 295 kHz at $V_{DD}=15V$	High: 710 kHz at $V_{DD}=5V$ 885 kHz at $V_{DD}=10V$ 2800 kHz at $V_{DD}=15V$
Input Capacitance	Low: Average 1 to 2 pF Peak 2 to 4 pF	High: Average 2 to 3 pF Peak 5 to 10 pF
Noise Margin	Excellent: 1.0V at $V_{DD}=5V$ 2.0V at $V_{DD}=10V$ 2.5V at $V_{DD}=15V$	Good: 0.5V at $V_{DD}=5V$ 1.0V at $V_{DD}=10V$ 1.0V at $V_{DD}=15V$
Output Transition Time	200 ns (typ.) at $V_{DD}=5V$ $C_L = 50$ pF	50 to 100 ns at $V_{DD}=5V$ $C_L = 50$ pF

GENERAL OPERATING AND HANDLING INSTRUCTIONS

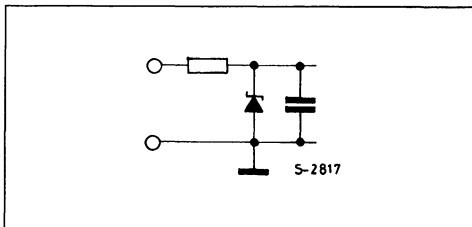
Power Source Rules

- Referring to standard input network protection of fig. B, when separate power supplies are used for V_{DD} and for the device inputs, the V_{DD} supply should always be turned on before the input signal source and the input signal should be turned off before the V_{DD} supply is turned off. This rule will prevent the D1 input protection diode from overdissipation and possible damage when the device power supply is grounded. When the device power supply is an open circuit, violation of this rule can result in undesired circuit operation although device damage may not result; AC inputs can be rectified by D1 input diode to act as a power supply.
- The steady power-supply operating voltage should be kept within the recommended operating conditions and always below the maximum ratings.
- The power-supply polarity for COS/MOS circuits should not be reversed. The positive (V_{DD}) terminal should never be more than 0.5V negative with respect to the negative (V_{SS}) terminal ($V_{DD}-V_{SS} > -0.5V$). Reversal of polarities will forward-bias and short the structural and protection diode between V_{DD} and V_{SS} .

- Power-source current capability should be limited to the minimum value which will assure good logic operation.
- Large values of resistors in series with V_{DD} or V_{SS} should be avoided; transient turn-on of input protection diodes can result from drops across such resistors during switching.

A good practice is to use a zener protection diode in parallel with the power bus as shown in fig. H below. The zener value should be above the expected maximum regulation excursion, but should not exceed the maximum supply voltage. A current limiting resistor is included if the supply impedance is lower than the zener power dissipation rating to allow for a given zener voltage. The shunt capacitor value is chosen to supply required peak current switching transients.

Fig. H



Input Signal Rules

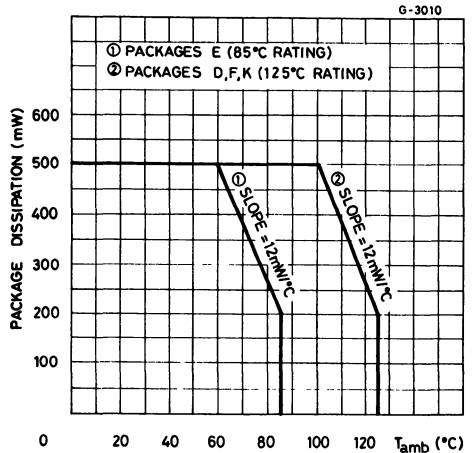
- 1) Signals should not be applied to the inputs while the device power supply is off unless the input current is limited to a steady-state value of less than 10mA. Input-signal interfaces that swing the allowable 0.5V above V_{DD} or below V_{SS} should be current-limited to 10mA or less. Whenever the possibility of exceeding 10mA of input current exists, a resistor in series with the input must be used. The value of this resistor can be as high as 10kΩ without affecting static electrical characteristics. However, speed will be reduced because of the added RC time constant. Particular attention should be given to long input-signal lines where high inductance can increase the likelihood of large-signal pickup in noisy environments. In these cases, series resistance with shunt capacitance at the IC input terminals is recommended. The shunt capacitance should be made as large as possible consistent with the system speed requirements.
- 2) All COS/MOS inputs should be terminated correctly. When COS/MOS inputs are wired to edge card connectors with COS/MOS drive coming from another PC board, a shunt resistor should be connected to V_{DD} or V_{SS}.
- 3) When COS/MOS circuits are driven by TTL logic a pull-up resistor should be connected from the COS/MOS inputs to 5V.
- 4) Input signals should be maintained within the recommended input signal swing range.
- 5) Input rise and fall times for clocked devices must not exceed 15 μs in order to avoid high power consumption, false triggering, etc. With slower inputs a Schmitt trigger must be employed.

Output Rules

- 1) The power dissipation in a COS/MOS package should not exceed the rated value for the ambient temperature specified. The actual dissipation should be calculated when (a) shorting outputs directly to V_{DD} or V_{SS}, (b) driving low-impedance loads, or (c) directly driving the base of PNP or NPN bipolar transistors.
- 2) Output short circuits often result from testing errors or improper board assembly. Shorts on buffer outputs on power supplies greater than 5V can damage COS/MOS devices.
- 3) COS/MOS, like active pull-up TTL, cannot be connected in the "wire-OR" configuration be-

- cause an "on" PMOS and an "on" NMOS transistor could be directly shorted across the power-supply rails. For applications with wire OR configurations it is necessary to use devices with tri-state logic outputs.
- 4) Paralleling gates is recommended only when the gates are within the same IC package.
- 5) Output loads should return to a voltage within the supply-voltage range (V_{DD} to V_{SS}).
- 6) Large capacitive loads (greater than 5000 pF) on COS/MOS buffers of high-current drivers act like short circuits and may over-dissipate output transistors.
- 7) Output transistors may be over-dissipated by operating buffers as linear amplifiers or using these types as one-shot or astable multivibrators.
- 8) Shorting of the output to V_{SS} or V_{DD} can cause the device power dissipation to exceed the safe value of 500 mW as shown in fig. 1. This is possible with supply voltage higher than 5V. For cases in which a short circuited load is driven directly (base of PNP or NPN bipolar transistor) the requirements for gate operation must be determined by consulting the published data. Note that a individual output transistor dissipation must be limited to 100 mW.

Fig. 1 - Standard COS/MOS Thermal Derating Chart



Noise Immunity and Noise Margin

DC Noise Immunity

The V_{IL} and V_{IH} characteristics define the maximum tolerable noise voltages at an input terminal when input signals are within 50 mV of supply lines.

Noise Margin

The noise margin voltage is the maximum voltage that can be added, at an input voltage $V_i = V_{OL}$ or V_{OH} of the preceding stage without upsetting the logic or causing the output to exceed the output voltage V_O .

In practice, DC noise immunity is much more significant than noise margin because the COS/MOS outputs are normally within 50mV of supply lines. Noise immunity increases if the input pulse width becomes less than the propagation delay of the circuit.

This condition is often described as AC noise immunity.

Handling

SGS-THOMSON has chosen a no-compromise strategy in the MOS ESD protection. From the wafer level to the shipping of finished units, we fully guarantee each work station and processing of the parts.

The supplier best commitment is useless if the end user does not provide the same level of protection

and care in application.

Here are the basic static control protection rules to comply with the rules the following procedures should be set up:

- a) Handling equipment, trays, table tops and transport carts should be conductive;
- b) Metal parts of fixtures, tools, soldering irons and table tops should be grounded to a common point;
- c) Operators should use grounded (metal or conductive) plastic wrist straps with a 1MΩ series resistor;
- d) Packages should not be removed from their conductive or antistatic carriers until required; this should only be done by a grounded operator. Devices removed should be placed in a conductive tray;
- e) All tests should be performed by a grounded operator and after completion of test, devices should be reinserted in conductive carriers;
- f) The printed circuit boards should have shorting bars installed prior to assembly (soldering). When possible COS/MOS IC's should be the last component to be installed on printed circuit boards.

Table I - STATIC ELECTRICAL CHARACTERISTICS (SGS-THOMSON 4000B and UB)

Parameter		Test Conditions				Values						Unit
		V_i (V)	V_O (V)	I_O (μA)	V_{DD} (V)	T_{Low}		25°C		T_{High}		
						Min.	Max.	Min.	Max.	Min.	Max.	
I_L (gates)	HCC types	0/ 5			5		0.25		0.25		7.5	μA
		0/10			10		0.5		0.5		15	
		0/15			15		1		1		30	
		0/20			20		5		5		150	
	HCF types	0/ 5			5		1		1		7.5	
		0/10			10		2		2		15	
		0/15			15		4		4		30	
I_L (buffer FF)	HCC types	0/ 5			5		1		1		30	μA
		0/10			10		2		2		60	
		0/15			15		4		4		120	
		0/20			20		20		20		600	
	HCF types	0/ 5			5		4		4		30	
		0/10			10		8		8		60	
		0/15			15		16		16		120	

Table I - STATIC ELECTRICAL CHARACTERISTICS 4000B and UB (Cont'd)

Parameter		Test Conditions				Values					Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low}		25°C		T _{High}		
						Min.	Max.	Min.	Max.	Min.		Max.
I _L (MSI)	HCC types	0/ 5			5		5		5		150	μ A
		0/10			10		10		20		300	
		0/15			15		20		20		600	
		0/20			20		100		100		3000	
	HCF types	0/ 5			5		20		20		150	
		0/10			10		40		40		300	
	0/15			15		80		80		600		
V _{OH}		0/ 5		< 1	5	4.95		4.95		4.95		V
		0/10		< 1	10	9.95		9.95		9.95		
		0/15		< 1	15	14.95		14.95		14.95		
V _{OL}		5/0		< 1	5		0.05		0.05		0.05	V
		10/0		< 1	10		0.05		0.05		0.05	
		15/0		< 1	15		0.05		0.05		0.05	
V _{IH} (B series)			0.5/4.5	< 1	5	3.5		3.5		3.5		V
			1/9	< 1	10	7		7		7		
			1.5/13.5	< 1	15	11		11		11		
V _{IL} (B series)			4.5/0.5	< 1	5		1.5		1.5		1.5	V
			9/1	< 1	10		3		3		3	
			13.5/1.5	< 1	15		4		4		4	
V _{IH} (UB series)			0.5/4.5	< 1	5	4		4		4		V
			1/9	< 1	10	8		8		8		
			2/13	< 1	15	12		12		12		
V _{IL} (UB series)			4.5/0.5	< 1	5		1		1		1	V
			9/1	< 1	10		2		2		2	
			13/2	< 1	15		3		3		3	
I _{OH}		HCC types	0/5	2.5		5	-2		-1.6		-1.15	mA
			0/5	4.6		5	-0.64		-0.51		-0.36	
			0/10	9.5		10	-1.6		-1.3		-0.9	
			0/15	13.5		15	-4.2		-3.4		-2.4	
		HCF types	0/5	2.5		5	-1.53		-1.36		-1.1	
			0/5	4.6		5	-0.52		-0.44		-0.36	
			0/10	9.5		10	-1.30		-1.1		-0.90	
			0/15	13.5		15	-3.6		-3		-2.4	

Table I - STATIC ELECTRICAL CHARACTERISTICS 4000B and UB (Cont'd)

Parameter		Test Conditions				Values						Unit
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low}		25°C		T _{High}		
						Min.	Max.	Min.	Max.	Min.	Max.	
I _{OL}	HCC types	0/5	0.4		5	0.64		0.51		0.36		mA
		0/10	0.5		10	1.6		1.3		0.9		
		0/15	1.5		15	4.2		3.4		2.4		
	HCF types	0/5	0.4		5	0.52		0.44		0.36		
		0/10	0.5		10	1.3		1.1		0.9		
		0/15	1.5		15	3.6		3		2.4		
I _{IL} I _{IH}	HCC types	0/18	Any input		18		±0.1		±0.1		±1	μA
	HCF types	0/15			15		±0.3		±0.3		±1	
I _{OL} , I _{OH}	HCC types	0/18			18		±0.4		±0.4		±12	μA
	HCF types	0/15			15		±1.0		±1.0		±7.5	
C _I								7.5				pF
C _I (UB)								22.5				pF

STANDARD JEDEC SPECIFICATIONS

Table II - ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply voltage	-0.5 to 18	V
V _I	Input Voltage	-0.5 to V _{DD} +0.5	V
I _I	DC input current (any input)	± 10	mA
T _{stg}	Storage temperature range	-65 to 150	°C

Table III - RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply voltage	3 to 15	V
V _I	Input Voltage;	0 to V _{DD}	V
T _{op}	Operating temperature – for extended range devices – for intermediate range devices	-55 to 125 -40 to 85	°C

Table IV - STATIC ELECTRICAL JEDEC CHARACTERISTICS

Parameter		Test Conditions				Values						Unit
		V _i (V)	V _o (V)	I _o (μ A)	V _{DD} (V)	T _{Low}		25°C		T _{High}		
						Min.	Max.	Min.	Max.	Min.	Max.	
I _L (gates)	HCC				5		0.25		0.25		7.5	μ A
					10		0.5		0.5		15	
					15		1		1		30	
	HCF				5		1		1		7.5	
					10		2		2		15	
					15		4		4		30	
I _L (buffer FF)	HCC				5		4		4		30	μ A
					10		8		8		60	
					15		16		16		120	
	HCF				5		4		4		30	
					10		8		8		60	
					15		16		16		120	
I _L (MSI)	HCC				5		5		5		150	μ A
					10		10		10		300	
					15		20		20		600	
	HCF				5		20		20		150	
					10		40		40		300	
					15		80		80		600	
V _{OL}		0/ 5		< 1	5		0.05		0.05		0.05	V
		0/10		< 1	10		0.05		0.05		0.05	
		0/15		< 1	15		0.05		0.05		0.05	
V _{OH}		5/0		< 1	5	4.95		4.95		4.95		V
		10/0		< 1	10	9.95		9.95		9.95		
		15/0		< 1	15	14.95		14.95		14.95		
V _{IL}			0.5/4.5	< 1	5		1.5		1.5		1.5	V
			1/9	< 1	10		3		3		3	
			1.5/13.5	< 1	15		4		4		4	
V _{IH}			4.5/0.5	< 1	5	3.5		3.5		3.5		V
			9/1	< 1	10	7		7		7		
			13.5/1.5	< 1	15	11		11		11		
I _{OL}	HCC	0/5	0.4		5	0.64		0.51		0.36		mA
		0/10	0.5		10	1.6		1.3		0.9		
		0/15	1.5		15	4.2		3.4		2.4		
	HCF	0/5	0.4		5	0.52		0.44		0.36		
		0/10	0.5		10	1.3		1.1		0.9		
		0/15	1.5		15	3.6		3		2.4		
I _{OH}	HCC	0/5	4.6		5	-0.25		-0.2		-0.14		mA
		0/10	9.5		10	-0.62		-0.5		-0.35		
		0/15	13.5		15	-1.8		-1.5		-1.1		
	HCF	0/5	4.6		5	-0.2		-0.16		-0.12		
		0/10	9.5		10	-0.5		-0.4		-0.3		
		0/15	13.5		15	-1.4		-1.2		-1.0		
I _I	HCC	0/15			15		\pm 0.1		\pm 0.1		\pm 1	μ A
	HCF	0/15			15		\pm 0.3		\pm 0.3		\pm 1	μ A
C _I									7.5			pF

MILITARY / CECC PRODUCTS

SGS-THOMSON is a leading supplier of high-reliability integrated circuits devoted to those applications (military, medical, telecom, nuclear instruments, aerospace etc.) where reliability must be guaranteed or certified for each and every lot. The philosophy of "zero failure" in hi-rel products has lead SGS-THOMSON to obtain approval from many important international inspection authorities: ESA/SCC, Italian Ministry of Defence, BSI, CECC, CNET, Association of Electronic Industries in Singapore, and so on.

Two of the additional screening procedures SGS-THOMSON can offer are standardized and are intended to provide the user with:

- a standard process flow to reduce costs and delivery time, due to the totally automated management of the production;
- logic families screened according to military specifications.

The two different screening levels are "SGS-THOMSON PLUS" and MIL STD 883C Lev. B. The former undergoes a level of screening between that of the standard production and the MIL STD 883C. Moreover all screening levels of CECC are available since SGS-THOMSON in an approved manufacturer. G-REL integrated circuits are supplied in hermetically sealed packages that have been de-

veloped to meet the requirements of military, aerospace and critical industrial applications.

Packages supplied include:

- ceramic dual in line metal sealed
- ceramic dual in line frit sealed
- ceramic leadless chip carrier
- ceramic flat

SGS-THOMSON PLUS PROGRAM

CMOS 4000B is available screened according to the SGS-THOMSON PLUS flow chart described in Table 1. The SGS-THOMSON PLUS program is a modification of the MIL STD 883C maintaining a very high quality level with the right ratio quality/price for customers whose production is not intended for military applications demanding lot release and certification. The electrical screening is performed 100% before and after the Burn-in test. All the electrical parameters listed in the datasheets are 100% tested.

Group A acceptance tests are performed as shown in Table 2.

Table 1- SGS-THOMSON PLUS SCREENING FLOW

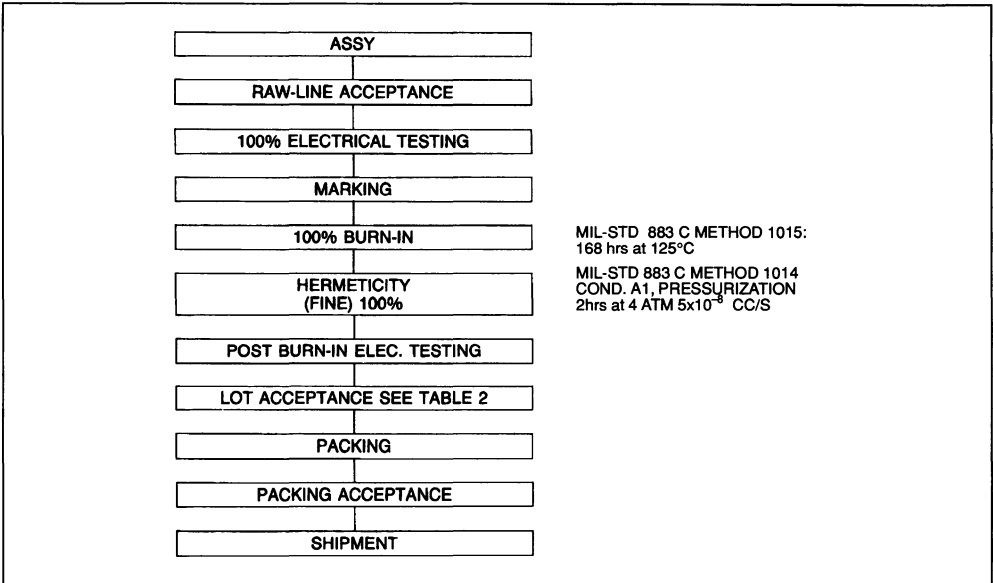


Table 2 - OUTGOING QUALITY CONTROL

Test	Mil Std883c Method	Inspection Level	Acceptable Quality Level (AQL)	Notes
VISUAL & MECHANICAL	2009	I	0.04	CUMULATIVE MAJOR + MINOR DEFECTS
INOOPERATIVE FAILURES PARAM. DC PARAM. AC	-	II	0.04	CUMULATIVE (INOOPERATIVE + DC PARAMETERS OVER GUARANTEED TEMPERATURE RANGE)
RESISTANCE TO SOLVENTS	2015	S3	0.65	
SOLDERABILITY	2003	S3	0.65	
HERMETICITY	1014	II	0.15	FINE AND GROSS LEACAGES

MIL-STD 883 C LEVEL B

All the HCC devices are available in ceramic packages, processed and screened according to the MIL-STD 883C Lev. B, flow chart shown in Table 3. Quality conformance inspection procedures are

conducted as described in the Group A, B, C, and D tests of the MIL-STD 883C Method 5005. A certificate of conformity is issued and included with each shipment.

Table 3 - Screening Flow for MIL-STD-883C Lev. B Method 5004

Screen	Condition Method	REQMT
INTERNAL VISUAL	2010 TEST COND. B	100%
STABILIZATION BAKE	1008	100%
TEMPERATURE CYCLING	1010 TEST COND. C	100%
CONSTANT ACCELERATION	2001 TEST COND. E	100%
SEAL: FINE GROSS	1014	100%
PREBURN-IN ELECTRICAL PARAMETERS	PER APPLICABLE DEVICE SPECIFICATION	*
BURN-IN TEST	1015 168 hrs 125°C	100%
POST-BURN-IN ELECTRICAL PARAMETERS	PER APPLICABLE DEVICE SPECIFICATION	100%
FINAL ELECTRICAL TEST: STATIC TEST: 1. 25°C (SUBGROUP I, TABLE I 5005) 2. MAX AND MIN. RATED OPERATING TEMP. (SUBGROUP 2, 3 TABLE I 5005) DYNAMIC TESTS AND SWITCHING TEST 25°C (SUBGROUP 4, 9 TABLE I, 5005)	PER APPLICABLE DEVICE SPECIFICATION	100% 100% 100%
FUNCTIONAL TEST 25°C (SUBGROUP 7, TABLE I, 5005)		100%
EXTERNAL VISUAL	2009	100%

* 100% for devices which require data calculation as defined in MIL-STD-883C METHOD 5004.

CECC QUALIFIED

Most of the devices of CMOS 4000B family are available qualified and released according to CECC 90000 specifications. Each shipment is relased with the official CECC certificate and each device shows the official CECC logo. SGS-THOMSON offers

screening according to levels B, C, D, E, F, and H. In all cases lot acceptance is made with AQLs according to the assessment level R which is the most severe.

The screening flow of all levels is shown in Tab. 4, 5, and 6.

Table 4 - CECC SCREENS AND TESTS DESCRIPTION

Screen or Test Number	Screen or Test	Reference to CECC 90 000 Unless Otherwise Stated	Conditions
1	Internal visual examination	4.2.1	See Appendix A of CECC 90 000
2	Storage at high temperature	4.6.1	T = T _{stg} max. t = 24 hrs min. No final measurement
3	Change of temperature	4.6.8	T _{min} = T _{stg} min. T _{max} = T _{stg} max 10 cycles. No final measurement
4	Acceleration steady state	4.6.7	Acceleration = 294 000 m/s ² (30 000 gn) unless otherwise specified Direction = Y ₂ . No final measurement
5	External visual examination (optional)	4.2.2	4.2.2
6	Sealing a: tracer gas method with mass spectrometer b: gross leak	4.6.9.1 4.6.9.2	Test QK Test QC
7	Particle impact noise detection	under consideration	under consideration
8	Serialization	-	-
9	Electrical test (pre burn-in)	CECC 90 100	As for Sub-Groups A2 and A3 of relevant DS unless specified
10.1	Burn-in	-	T = max. operating temperature, t = 240 hrs min. Electrical conditions as specified in the DS
10.2	Burn-in	-	T _{amb} = 125 °C unless otherwise limited by the technology when a lower limit is specified in the family or DS. t = 168 ^{±9} hrs or any equivalent combination of it. Electrical conditions as specified in the DS
11	Electrical tests (post burn-in)	-	As for Sub-Groups A2 and A3 of relevant DS unless otherwise specified. The DS will prescribe the maximum deviations allowable from the results recorded in the preceding electrical tests
12	Reverse bias burn-in	-	T _{amb} = 150 °C unless otherwise limited by the technology when a lower limit is specified in the family or Ds. t = 72 hrs min. Electrical conditions as specified in the DS
13.1	Final electrical tests	-	As for Sub-Groups A2, A3, A4a, A4b, and A5 of the relevant DS
13.2	Final electrical tests	-	As for Sub-Groups A2 and A3 of the relevant DS
14	Radiographic	Under consideration	Under consideration
15	Electrical tests at max. operating temperature	-	As for Sub-Groups A4a of the relevant DS unless otherwise specified
16	External visual examination	4.2.2	4.2.2

Table 5 - SCREENING PROCEDURES: FLOW DIAGRAMS (Screen test number at left of each block)

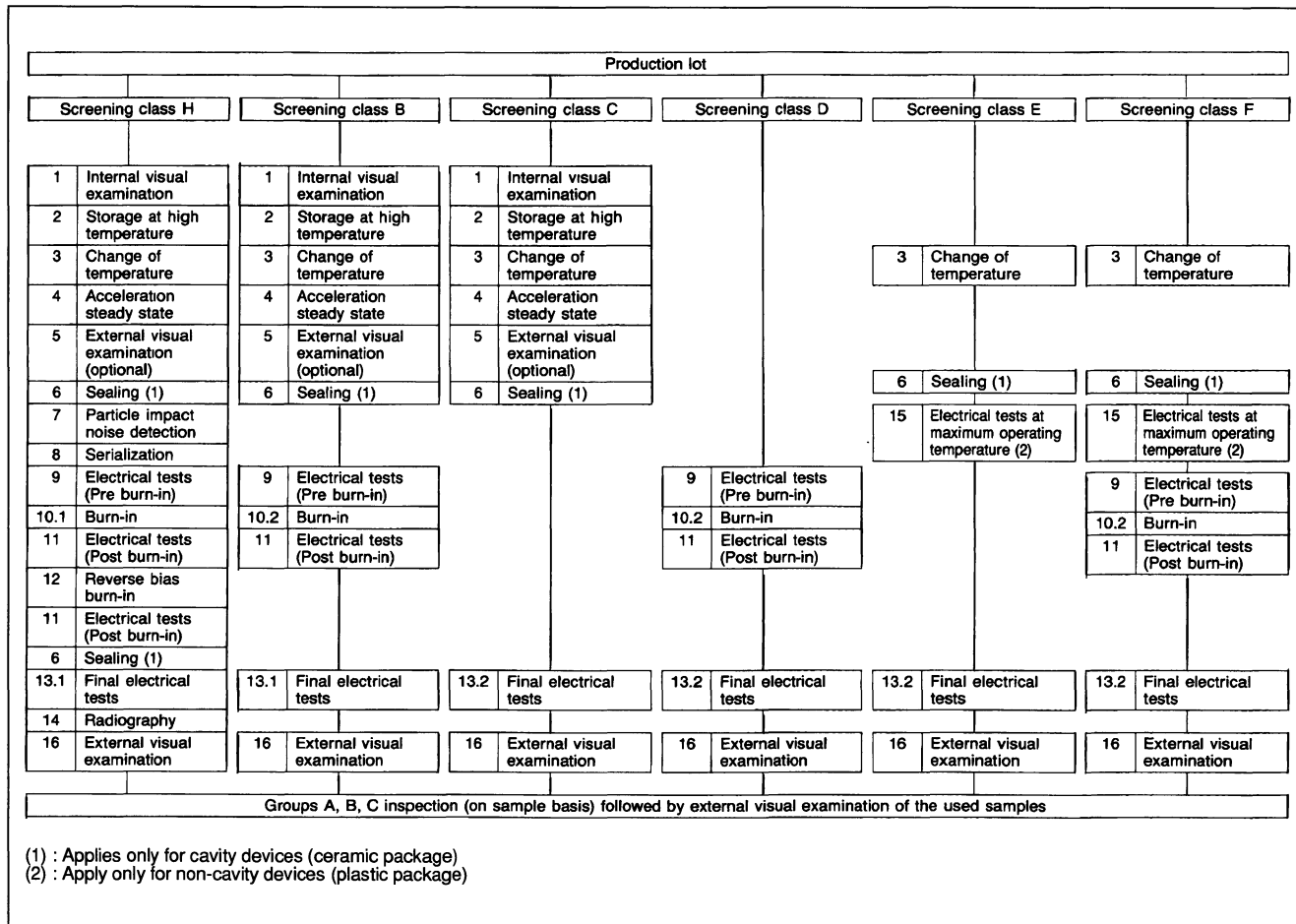


Table 6 - CECC INSPECTION GROUPS AND TEST CONDITION

Examination or test	D ND (1)	Inspection requirements	
		Assessment levels	
		R	
GROUP A INSPECTION		IL	AQL
Sub-Group A1 Visual examination	ND	I	0.04
Sub-Group A2 Verification of the function	ND	II	0.04
Sub-Group A3 Static characteristics at 25°C	ND	II	0.04
Sub-Group A4a Static characteristics at maximum operating temperature	ND	II	0.04
Sub-Group A4b Static characteristics at minimum operating temperature	ND	S-4	1.0
Sub-Group A5 Dynamic characteristic at 25°C	ND	II	0.065

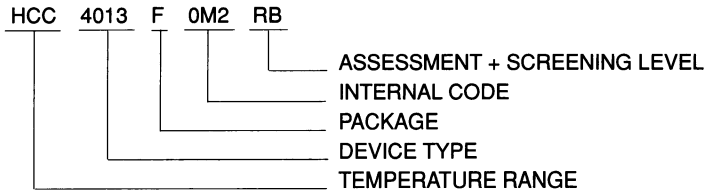
GROUP B INSPECTION		Assessment levels	
		R	
		IL	AQL
Sub-Group B1 Dimensions	ND	S-4	1.0
Sub-Group B2 Solderability	D	S-3	2.5
Sub-Group B3 Sealing test	ND	II	1.0
Sub-Group B4 Change of temperature Followed by: 1) For cavity packages: Fine and gross leak test 2) For non-cavity packages: Damp heat accelerated End point tests: Electrical tests as for Sub-Groups A2 and A3	ND ND D	S-4	2.5
Sub-Group B5 Electrical endurance 168hrs End point tests: Electrical tests as for Sub-Groups A2 and A3	ND	S-4	1.5

Note: 1) D = Destructive test
ND = Non destructive test

For more detailed information see CECC 90-100 issue 2 specs.

CECC CMOS

ORDERING CODE:



TEMPERATURE RANGE

HCF	Standard (- 40°C to + 85°C)
HCC	Extended (- 55°C to + 125°C)

PACKAGES:

B	Plastic Dual in Line
F	Ceramic Dual in Line Frit Seal
K @	Ceramic Flat (For Level RH only)
D @	Ceramic Dual in Line Metal Sealed (For Level RH only)
Z @	Ceramic Leadless Chip Carrier (CLCC - For Level RH only)

@ = Production plant to be Qualified

ASSESSMENT + SCREENING LEVELS

RB	See the Screening Levels Table on page 32
RC *	See the Screening Levels Table on page 32
RD	See the Screening Levels Table on page 32
RE	See the Screening Levels Table on page 32
RF	See the Screening Levels Table on page 32
RH @	See the Screening Levels Table on page 32

* = Available on big demand only.

@ = Production plant to be Qualified.

DETAILED LIST OF APPROVED DEVICES

Type	CECC Spec. N°	Type	CECC Spec. N°
4001B	90104 / 105	4060B	90104 / 213
4002B	90104 / 106	4066B	90104 / 138
4006B	90104 / 107	4068B	90104 / 139
4007UB	90104 / 108	4069UB	90104 / 140
4008B	90104 / 109	4070B	90104 / 187
4011B	90104 / 110	4071B	90104 / 141
4012B	90104 / 111	4072B	90104 / 142
4013B	90104 / 112	4073B	90104 / 143
4014B	90104 / 113	4075B	90104 / 144
4015B	90104 / 114	4076B	90104 / 145
4016B	90104 / 115	4077B	90104 / 146
4017B	90104 / 170	4078B	90104 / 147
4018B	90104 / 171	4081B	90104 / 148
4019B	90104 / 172	4082B	90104 / 149
4020B	90104 / 116	4085B	90104 / 226
4021B	90104 / 117	4093B	90104 / 214
4022B	90104 / 118	4094B	90104 / 188
4023B	90104 / 119	4098B	90104 / 224
4024B	90104 / 120	4099B	90104 / 150
4025B	90104 / 121	4502B	90104 / 152
4027B	90104 / 122	4503B	90104 / 175
4028B	90104 / 123	4508B	90104 / 155
4029B	90104 / 124	4510B	90104 / 156
4030B	90104 / 125	4511B	90104 / 157
4032B	90104 / 126	4512B	90104 / 158
4034B	90104 / 127	4514B	90104 / 159
4035B	90104 / 128	4515B	90104 / 160
4038B	90104 / 129	4516B	90104 / 161
4040B	90104 / 130	4517B	90104 / 162
4042B	90104 / 185	4518B	90104 / 163
4043B	90104 / 186	4520B	90104 / 165
4044B	90104 / 132	4527B	90104 / 168
4046B	90104 / 212	4532B	90104 / 178
4047B	90104 / 225	4536B	90104 / 218
4049UB	90104 / 133	4538B	90104 / 179
4050B	90104 / 134	4555B	90104 / 199
4051B	90104 / 135	4556B	90104 / 181
4052	90104 / 136	4585B	90104 / 203
4053	90104 / 137		

**HARMONIZED SYSTEM OF QUALITY ASSESSMENT FOR ELECTRONIC COMPONENTS
CECC** **ECQAC**

CERTIFICATE OF APPROVAL OF MANUFACTURER

REGISTRATION NUMBER: **P 0018** ISSUE NUMBER: **3**
 OF **SGS-THOMSON Microelectronics S.r.l.**
 AT THEIR PLACE(S) OF WORK **Stradale Primatesta, 88**
I-95121 CATANIA

IN RESPECT OF GENERIC/~~SECURITY~~ SPECIFICATION CECC NUMBER **9090**
 TITLE: **- MONOLITHIC INTEGRATED CIRCUITS**

THE ORGANIZATION, FACILITIES AND INSPECTION PROCEDURES AT THE ABOVE PLACE OF WORK HAVE BEEN FOUND TO COMPLY WITH THE REQUIREMENTS OF DOCUMENT CECC 00 100 FOR QUALITY ASSESSMENT IN RESPECT OF THE FAMILIES OF COMPONENTS LISTED IN THE APPROVAL DOCUMENT(S) **NO 9090SGSC**
 THIS CERTIFICATE DOES NOT AUTOMATICALLY ENTITLE THE MANUFACTURER TO USE THE MARK OR CERTIFICATE OF CONFORMITY. THE APPROVAL OF ANY PARTICULAR TYPE OF ELECTRONIC COMPONENT IS THE SUBJECT OF A SEPARATE CERTIFICATE.

PLACE: **MILANO**
 DATE: **27 September 1990**

IMQ
 ISTITUTO ITALIANO DEL MARCHIO DI QUALITÀ
Antonio Seda

CECC
 CENELEC Electronic
 Components Committee
ECQAC
 Electronic Components
 Quality Assurance Committee

NOTE: This certificate is valid only in conjunction with the approval document(s) **No 9090SGSC**

This approval and this Certificate may be suspended or withdrawn in accordance with CECC 00 100 implemented in CEI - CCE 00 100.
 They may be suspended or withdrawn if no capability approval or qualification approval of a Components has been granted within one year of its date of issue.
 This certificate remains the property of the body which granted it.

IMQ
 20138 Milano - Via Quintiliano 43



RADIATION HARDENED PRODUCTS

Radiation Hardened versions of **HCC 4000** series types are offered by SGS-THOMSON for special applications in Space, Biomedical and Military fields.

These devices are supplied in accordance to the relevant Hi-Rel processing and screening specifications requested in the particular field (MIL 883, SCC9000, etc) and are electrically and mechanically identical to their non-hardened equivalent.

The actual radiation resistance of SGS-THOMSON RAD-HARD C-MOS parts can vary slightly from lot to lot and from type to type, but has repeatedly been demonstrated (see fig. 1) to be far in excess of the limit of 100K rads, normally requested for space and chosen by SGS-THOMSON as a standard reference for certification.

By changing the diffusion of the basic CMOS process, a rad-hard capability of total dose is achieved up to 1.10^5 rads (Si). These rad-hard devices are processed according to ESA/SCC 9000 specifications and these types are subjected to a special process that monitors the tolerances more efficiently. The flow-chart is shown in Table 1.

The radiation exposure changes the levels of threshold voltages and leakage currents as shown in the figure below, thus a different diffusion process is necessary to monitor the effects of the radiation. Pre- and post-radiation measurements are made of threshold, threshold delta, leakage current and go, no-go functional tests in order to ensure that shift and absolute values are within the specified limits. ESA/SCC screening levels and tests are shown in the following pages. See list of qualified devices, page 45.

Fig. 1 - Example of Threshold drifts versus radiation dose as measured on a sample of SGS-THOMSON RAD-HARD production tested by an independent laboratory. Parts tested were guaranteed to withstand 100K rads, but all show voltage threshold shifts well inside radiation spec limits even at 300K rads (courtesy Hahn Meitner Institute, Berlin).

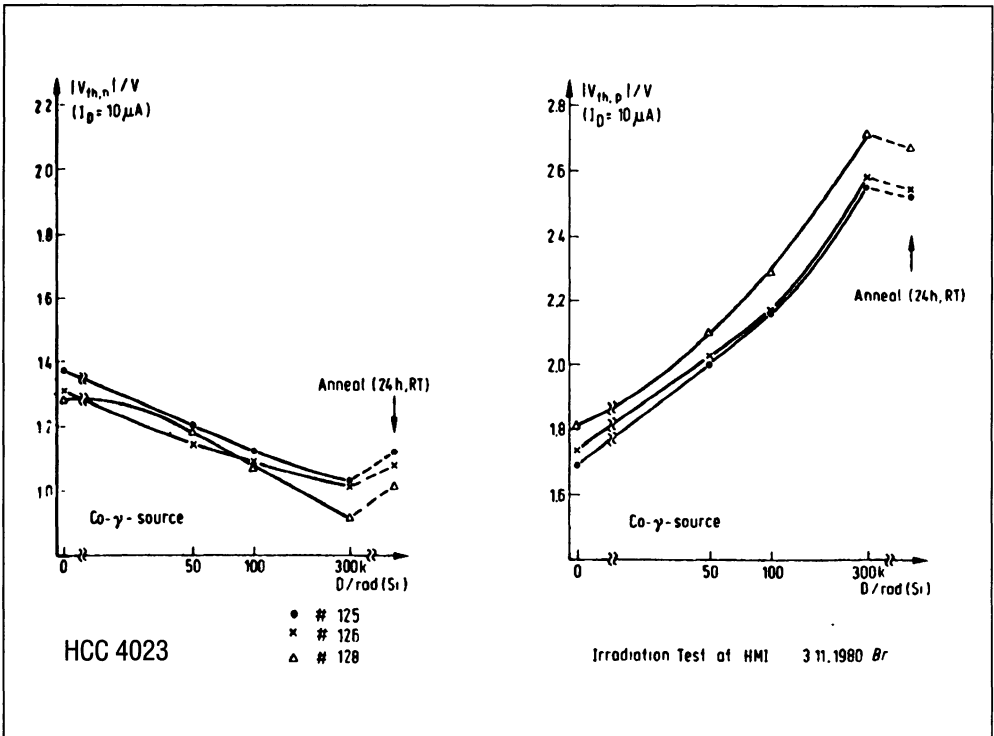


Table 1 - ESA/SCC GENERIC SPECIFICATION 9000

CHART II - FINAL PRODUCTION TEST

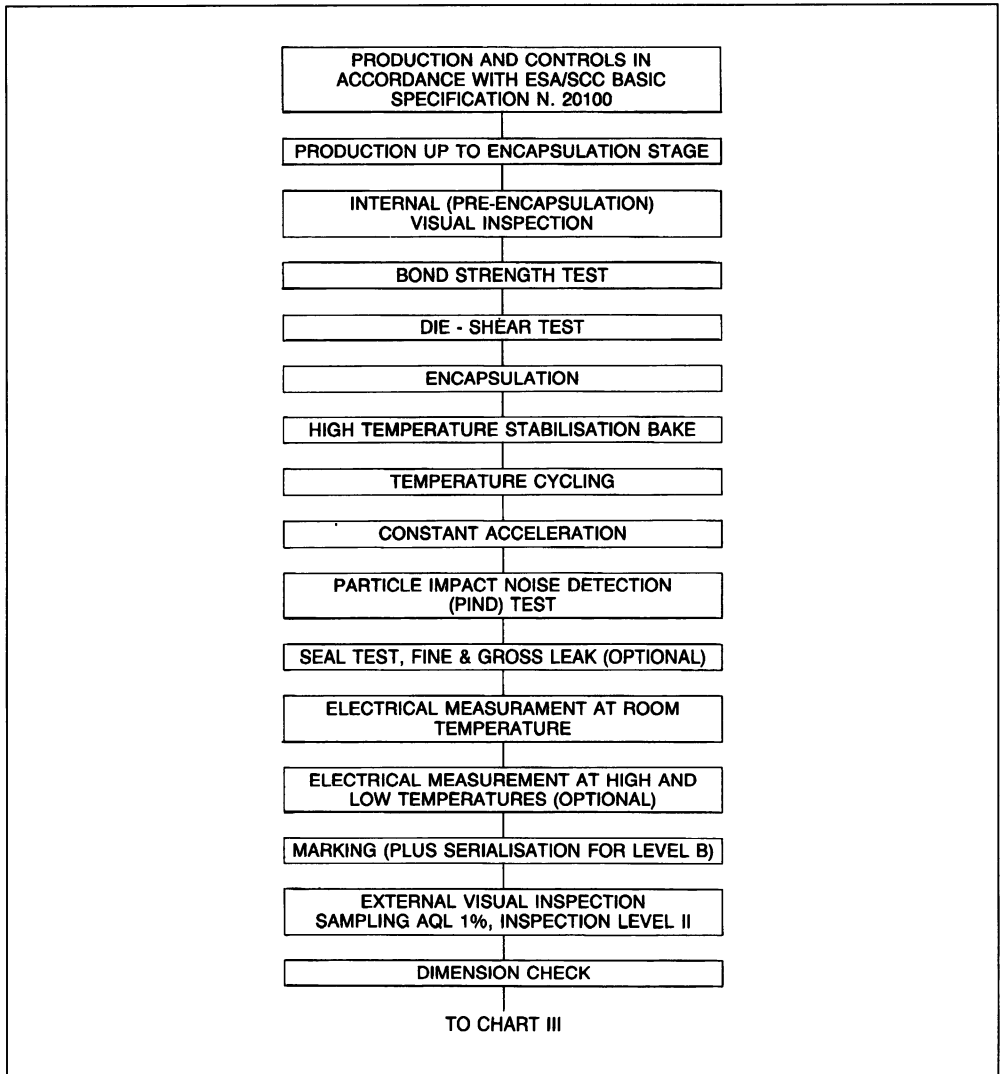
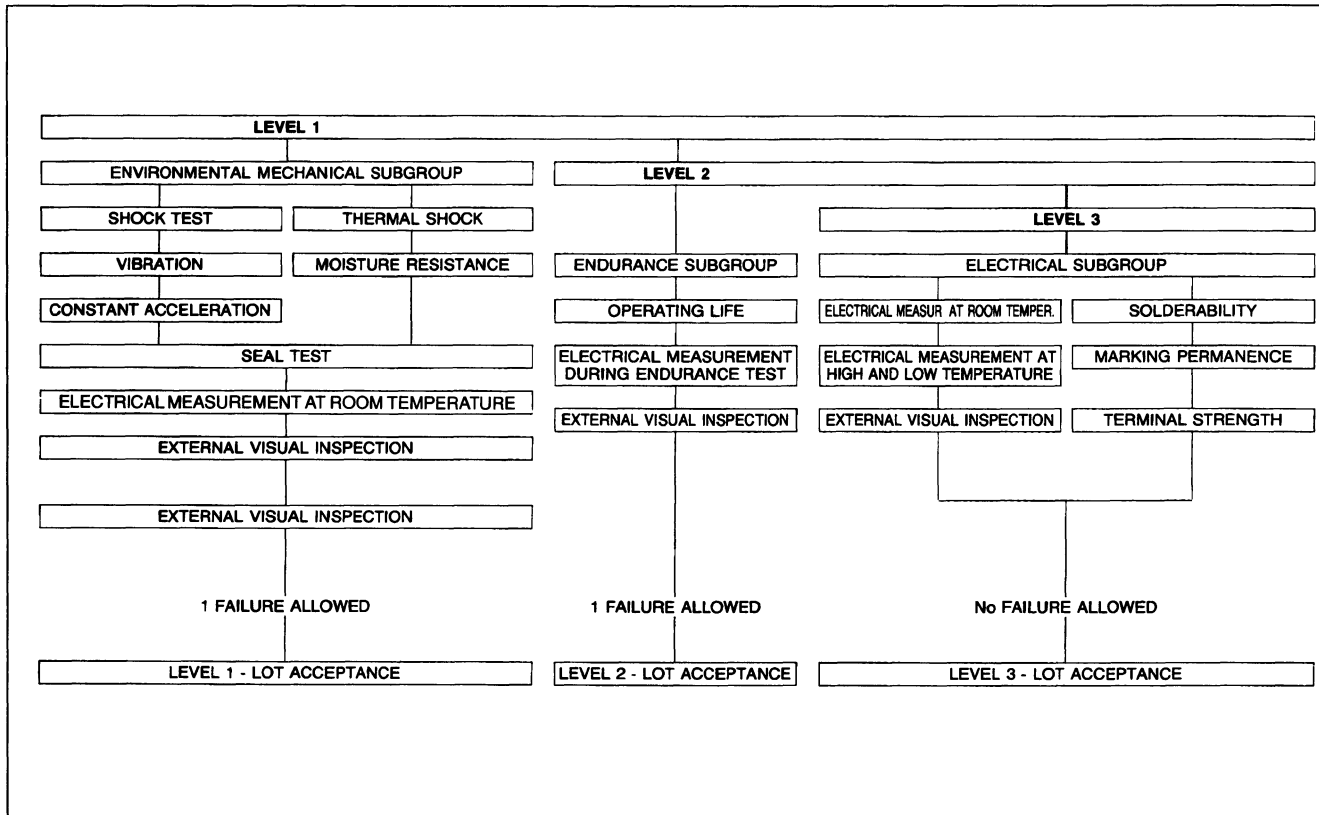


CHART III - BURN-IN – AND ELECTRICAL MEASUREMENTS

	TESTING LEVELS	
	B	C
COMPONENTS FROM FINAL PRODUCTION TEST		
PARAMETER DRIFT VALUE (INITIAL MEASUREMENTS)	X	
HIGH TEMPERATURE REVERSE BIAS BURN-IN	X	X
PARAMETER DRIFT VALUE (INTERMEDIATE MEASUREMENTS)	X	
POWER BURN-IN 240 hours - LEVEL "B" 168 hours - LEVEL "C"	X	X
PARAMETER DRIFT VALUE (FINAL MEASUREMENTS)	X	
ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES	X	X
ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE	X	X
RADIOGRAPHIC INSPECTION	X	
SEAL TEST (FINE AND GROSS LEAK)	X	X
EXTERNAL VISUAL INSPECTION	X	X
CHECK FOR LOT FAILURE	X	X
TO CHART V		

CHART V - LOT ACCEPTANCE TEST



Note: Level 1 includes Level 2 and Level 3
 Level 2 includes Level 3



**european space agency
agence spatiale européenne**

Certificate of Qualification No. 73 D

**This is to certify that SGS-THOMSON, Rennes, France
has been qualified by ESA for the supply of Integrated Circuits C MOS B
Series (See ESA/SCC QPL for Types)
for use in ESA space programmes, according to ESA/SCC Generic
Specification 9000 and applicable Detail Specifications (See ESA/SCC QPL)
as recommended by the Space Components Coordination Group.
This certificate is valid until April 1992.**

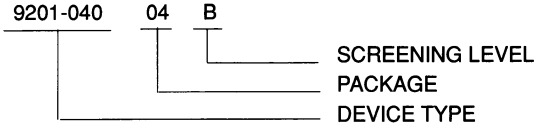
**Head of Product Assurance
and Safety Department**

A handwritten signature in black ink, appearing to read 'Jean-Louis'.

**Date
9 April 1990**

RADIATION-HARDENED CMOS

ORDERING CODE:



SCREENING LEVELS:

- B See Chart III, Page 41
- C See Chart III, Page 41

PACKAGES:

- 01 Ceramic Flat Gold Plated
- 02 Ceramic Flat Tin Plated
- 03 Ceramic Dual in Line Metal Sealed Gold Plated
- 04 Ceramic Dual in Line Metal Sealed Tin Plated
- 07 Leadless Ceramic Chip Carrier (LCCC)

MARKING:

Parts are marked with the ordering code.

DETAILED LIST OF APPROVED DEVICES

Type	SCC Spec. N°	Type	SCC Spec. N°	Type	SCC Spec. N°
4000B	9201 / 040	4021B	9306 / 016	4069UB	9401 / 010
4001B	9201 / 041	4022B	9204 / 023	4070B	9201 / 048
4002B	9201 / 042	4023B	9201 / 045	4071B	9201 / 063
4006B	9306 / 013	4024B	9204 / 024	4072B	9201 / 082
4007UB	9202 / 038	4025B	9201/046	4073B	9201 / 064
4008B	9202 / 039	40257B	9408 / 017	4075B	9201 / 065
40101B	9208 / 002	4026B	9406 / 001	4076B	9306 / 022
40103B	9204 / 036	4027B	9203 / 022	4077B	9201 / 055
40104B	9306 / 040	4028B	9205 / 010	4078B	9201 / 062
40105B	9306 / 033	4029B	9204 / 025	4081B	9201 / 052
40108B	9409 / 005	4030B	9201 / 047	4082B	9201 / 066
40107B	9401 / 013	4031B	9306 / 017	4085B	9201 / 067
40109B	9306 / 034	4034B	9306 / 025	4086B	9201 / 068
40109B	9407 / 003	4035B	9306 / 018	4089B	9202 / 060
4011B	9201 / 043	4040B	9204 / 026	4093B	9409 / 002
4012B	9201 / 044	4041UB	9202 / 040	4094B	9306 / 026
4013B	9203 / 023	4042B	9202 / 041	4095B	9206 / 003
4014B	9306 / 014	4043B	9202 / 042	4099B	9202 / 058
4015B	9206 / 015	4044B	9202 / 043	4502B	9401 / 006
4016B	9202 / 050	4045B	9202 / 026	4503B	9401 / 030
40160B	9204 / 047	4047B	9207 / 003	4506B	9202 / 063
40161B	9204 / 054	4048B	9201 / 054	4510B	9204 / 053
4017B	9204 / 020	4049UB	9202 / 045	4512B	9408 / 006
40174B	9203 / 038	4050B	9202 / 046	4614B	9408 / 012
4018B	9204 / 021	4051B	9202 / 047	4515B	9205 / 011
40181B	9202 / 068	4052B	9202 / 048	4516B	9204 / 045
40182B	9202 / 069	4053B	9202 / 049	4518B	9204 / 013
4019B	9202 / 051	4080B	9204 / 052	4520B	9204 / 028
40193B	9204 / 041	4083B	9209 / 001	4527B	9408 / 026
40194B	9306 / 032	4088B	9408 / 005	4532B	9202 / 065
4020B	9204 / 022	4087B	9408 / 009	4535B	9408 / 011
40206B	9301 / 009	4090B	9201 / 061	4536B	9408 / 025

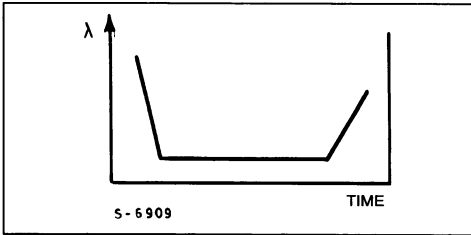
RELIABILITY REPORT

**RELIABILITY AND FAILURE MECHANISMS
FUNDAMENTALS**

-Through accelerated stresses we ascertain the value of the components failure rates, in terms of how many devices (in percent) are expected to fail every 1000 hours of operation (λ or F.R.)

-Failure rate versus time of activity shows the well-known trend.

-Failure rate



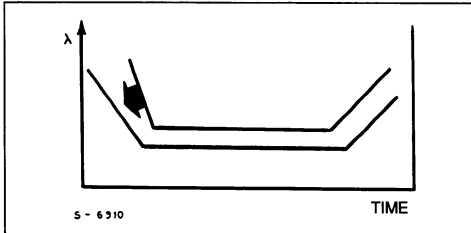
During the first time period the products are affected by the so-called "infant mortality" intrinsic to all semiconductor technologies. End users are very sensitive to this parameter which causes early operational failures in their equipment.

TARGETS

SGS-THOMSON periodically reviews and publishes lifetime results; at this time a new set of failure rate targets are being defined. These targets are translated into actual required test hours.

The goal is a steady shift of the limits.

Failure rate λ



TESTS

With accelerated tests we define the failure rate of the products, then, derating the data for different conditions, we know the life expectancy under the actual operating conditions.

In its simplest form the failure rate (at a given temperature) is:

$$F.R. = \frac{N}{D \cdot H} \quad (1)$$

Where N = Number of failures
D = Number of components
H = Number of testing hours

If we intend to determine the failure rate at other temperatures an acceleration factor must be considered.

Some tests are accelerated by means of increased temperature, based on the assumption of the Arrhenius law:

$$F.R. = Ae^{-E_a/KT_j} \quad (2)$$

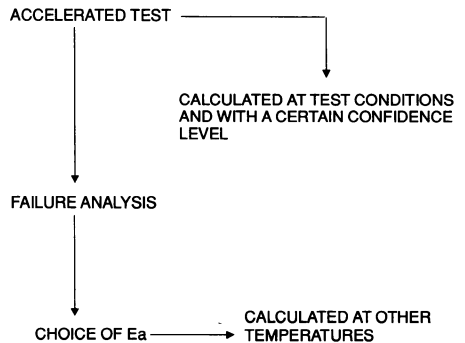
A = Constant
E_a = Activation energy
K = Boltzman's constant
T_j = Junction Absolute temperature

For two different temp. $F.R.(T_1)=F(T_1, T_2)F.R.(T_2)$

from (2) it is: $F(T_1, T_2) \equiv \text{EXP} \left[\frac{-E_a}{K} \left(\frac{1}{T_1} - \frac{1}{T_2} \right) \right]$ (3)

Clearly the choice of an appropriate activation energy, E_a is of paramount importance. The different mechanisms which could lead to circuit failure are characterized by specific activation energies whose values are published in the relevant literature.

THUS THE CORRECT PROCEDURE IS



RELIABILITY REPORT

Arrhenius equation (2) describes the rate of many processes responsible for degradation and failure of electronic components; it follows that if the transition of an item from an initial stable condition to a defined degraded state occurs by a thermally activated mechanism, then the time for the transition is given by an equation of the form:

$$MTBF = B \text{ EXP } (E_a/Kt)$$

MTBF = Mean time between failure

B = Temperature-independent constant

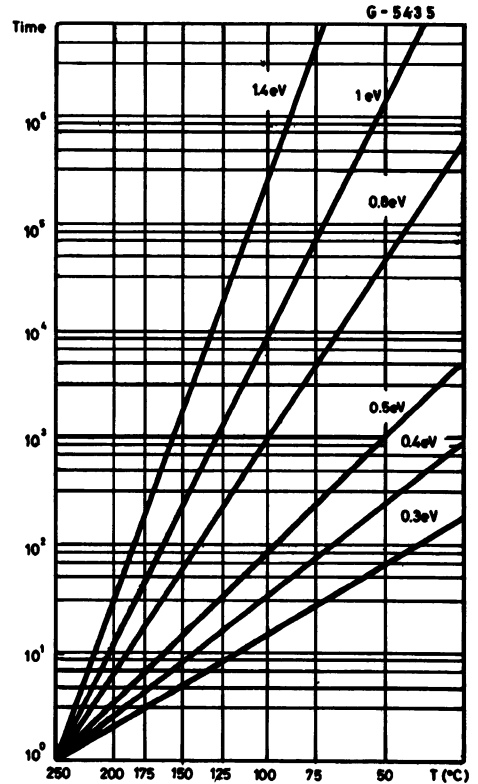
MTBF can be defined as the time to suffer a device degradation. The dramatic effect of the choice of the E_a value can be seen by plotting equation (2).

The acceleration effect of a 125°C device junction test with respect to 70°C actual device junction operation is equal to a factor of 100 for $E_a = 1\text{eV}$ and respectively 4 for $E_a = 0.3\text{eV}$.

Some words of caution are needed about published values of E_a :

- A) They are often related to high temperature test where a single E_a (with high value) mechanism has become significant.
- B) They are specifically related to the devices produced by that supplier (and to its technology) and in that period of time.
- C) They could be modified by the mutual action of other stresses (voltage, mechanical)
- D) Field device-application conditions should be considered.

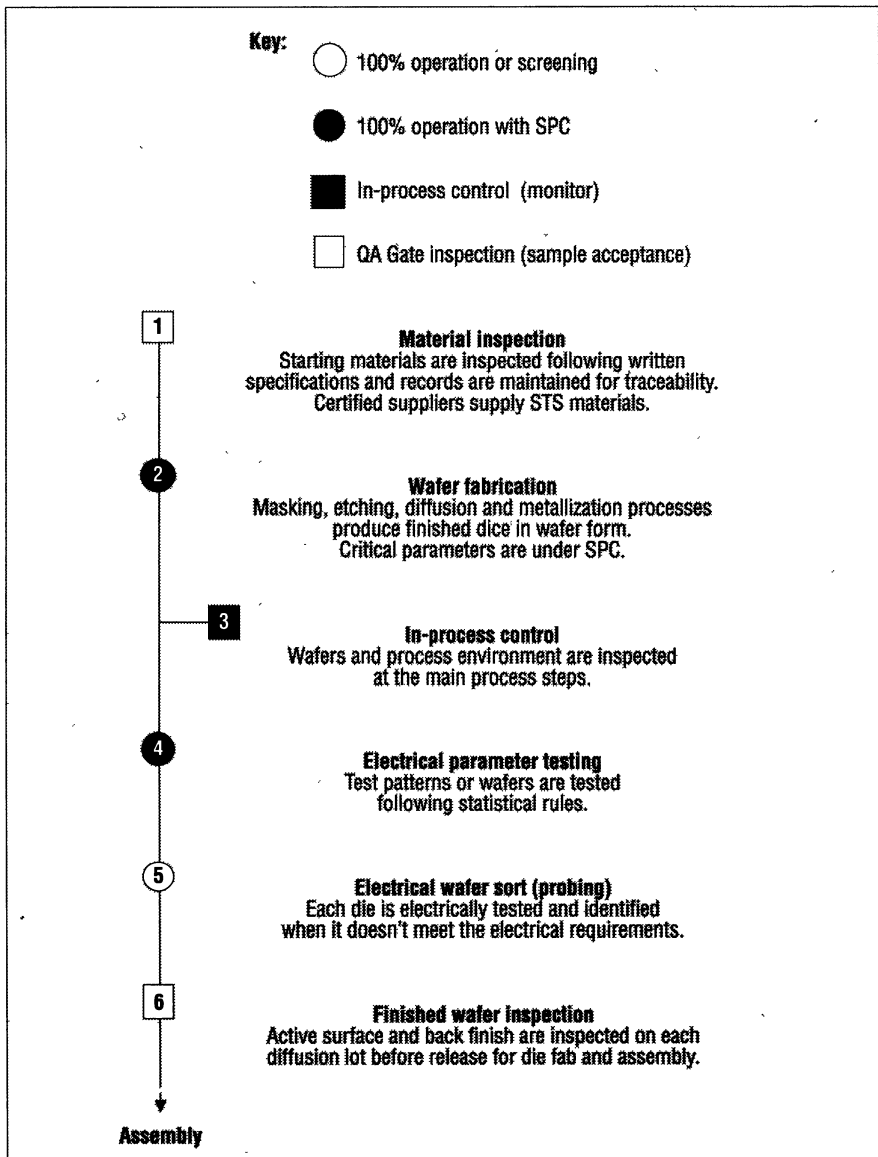
Life-Hours



Main Failure modes and relevant activation energies

Failure Mode	Activation Energy (eV)	Accelerating
SURFACE CHARGE	1.0 - 1.05	HIGH TEMPERATURE BIAS
IONIC CONTAMINATION	1.0 - 1.4	HIGH TEMPERATURE BIAS
DIELECTRIC DEFECTS	0.3 - 0.6	HIGH TEMPERATURE BIAS
ELECTROMIGRATION	0.5 - 1.2	HIGH TEMPERATURE BIAS
INTERMETALLIC GROWTH	1.0 - 1.05	HIGH TEMPERATURE BIAS, STORAGE
METAL CORROSION	0.3 - 0.8	HIGH HUMIDITY BIAS

WAFER FAB TYPICAL PRODUCTION PROCESS FLOW CHART

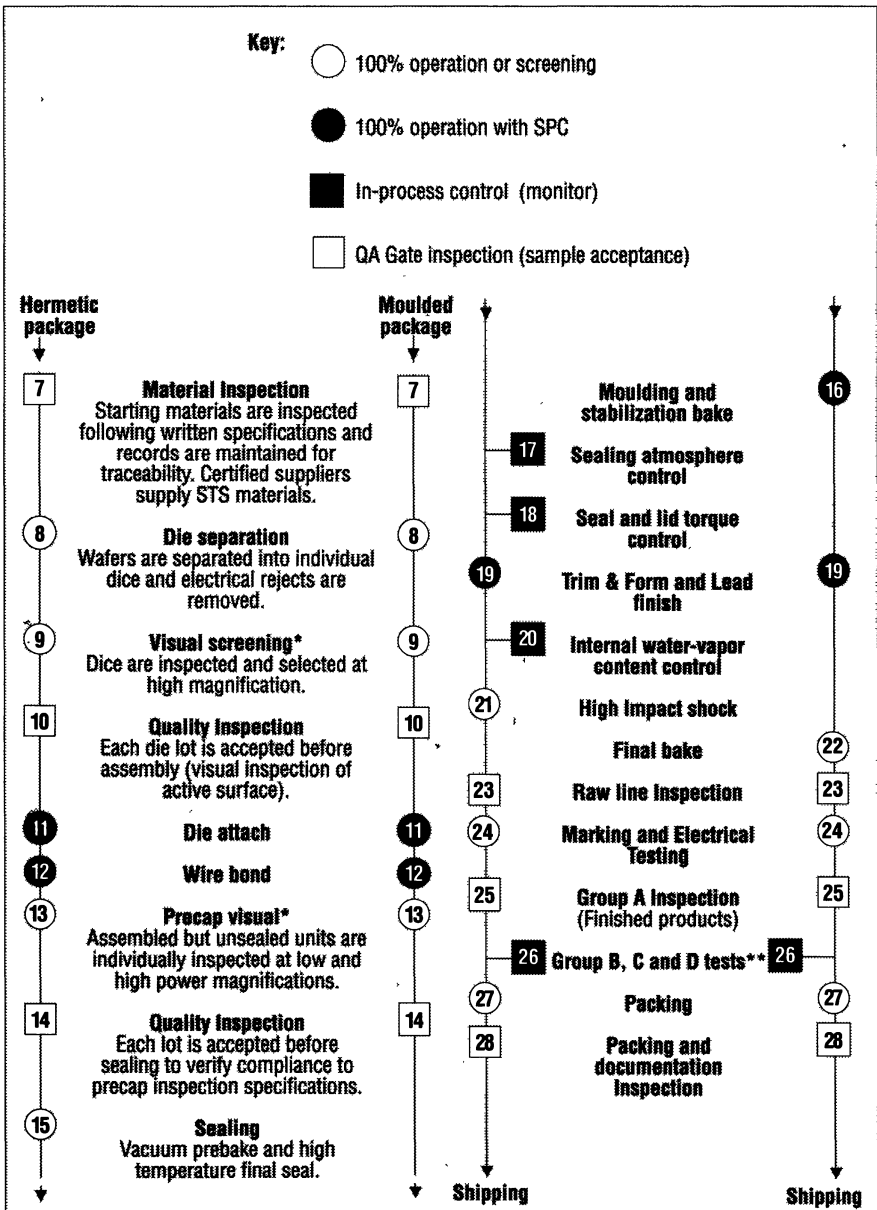


In-process control during wafer fabrication

The table emphasizes the most important fabrication steps with the relevant SPC measures and/or monitors performed.

PROCESS STEPS	IN-PROCESS INSPECTIONS/MONITORS
OXIDATION	<ul style="list-style-type: none"> - Visual - Thickness - Refractive Index - CV plot (stability of ionic concentration and contamination control)
DEPOSITION: Nitride, Poly Si	<ul style="list-style-type: none"> - Visual - Thickness - Refractive index - Doping content
PHOTOLITHOGRAPHY	<ul style="list-style-type: none"> - Mask and wafer cleanliness - Alignment and focusing accuracy - Critical dimensions
ETCHING	<ul style="list-style-type: none"> - Quality of etching and wafer cleanliness - Critical dimensions
DOPING BY IMPLANT (P, As, B)	<ul style="list-style-type: none"> - Sheet resistance (dose and implant uniformity)
DOPING BY DIFFUSION (POCl_3 , As)	<ul style="list-style-type: none"> - Sheet resistance - Thickness - CV plot (stability of ionic concentration and contamination control)
EPITAXIAL GROWTH	<ul style="list-style-type: none"> - Thickness - Resistivity - Crystal quality (stacking faults, bumps and others)
METALLIZATION	<ul style="list-style-type: none"> - Wafer cleanliness - Visual - SEM (step coverage and film quality) - Thickness - CV plot (stability of ionic concentration and contamination control)
INTERMEDIATE AND FINAL PASSIVATION	<ul style="list-style-type: none"> - Thickness - Doping content - Passivation integrity (density of pinholes and cracks) - Visual
BACK FINISHING	<ul style="list-style-type: none"> - Wafer thickness - Back metal thickness - Metal adherence
ELECTRICAL CHARACTERIZATION	<ul style="list-style-type: none"> - Main parameters for active and parasitic structures (e. g. threshold voltage, saturation current, hFE, resistances, capacitances ...)
WAFER INSPECTION	<ul style="list-style-type: none"> - Visual (microscope and/or laser surface inspection system)
ALL DEPOSITIONS AND PHOTOLITHOGRAPHY	<ul style="list-style-type: none"> - Surface Scan (to detect and to measure foreign particles)

ASSEMBLY TYPICAL PRODUCTION PROCESS FLOW CHART



* Omitted when the intrinsic quality meets the specified quality level

** For non military products, these reliability tests can be performed after step 23 on 100% electrically tested samples (when requested)

In-process control during assembly process

The table emphasizes the most important fabrication steps with the relevant SPC measures and/or monitors performed.

PROCESS STEPS	TESTS	DESCRIPTION
11	DIE ATTACH	–Integrated Circuits MIL-STD-883 Method 2010 cond B (internal visual) and Method 2019 (die shear strength); CECC 90000 –Discrete Devices MIL-STD-750 Method 2072 (internal visual) and Method 2017 (die shear strength); CECC 50000
12	WIRE BOND	– Integrated Circuits MIL-STD-883 Method 2010 cond. B (internal visual) and Method 2011 cond. D (bond strength); CECC 90000 – Discrete Devices MIL-STD-750 Method 2072 (internal visual) and Method 2037 (bond strength); CECC 50000
14	QUALITY INSPECTION	– Integrated Circuits MIL-STD-883 Methods 2010 cond. B (internal visual); CECC 90000 –Discrete Devices MIL-STD-750 Method 2072 (internal visual); CECC 50000
16	MOULDING AND STABILIZATION BAKE	– Visual and temperature process control
17	SEALING ATMOSPHERE CONTROL	Moisture content: < 200 ppm for Ceramic packages < 100 ppm for Metal Can packages
18	SEAL CONTROL	Fine Leak – Integrated Circuits MIL-STD-883 Method 1014 cond. A1 Helium leak detector after pressurization in He for: 2h at 5.1 atm Limit: 5×10^{-8} cc/s for ICV < 0.05 cc 4h at 5.1 atm Limit: 5×10^{-8} cc/s for ICV $\geq 0.05 < 0.5$ cc 2h at 3.0 atm Limit: 1×10^{-7} cc/s for ICV $\geq 0.5 < 1$ cc 5h at 3.0 atm Limit: 5×10^{-8} cc/s for ICV $\geq 1 < 10$ cc ICV = Internal Cavity Volume – Discrete Devices MIL-STD-750 Method 1071 cond. H1 Helium leak detector after pressurization in He for: 2h at 4.1 atm Limit: 5×10^{-8} cc/s for ICV < 0.4 cc 2h at 4.1 atm Limit: 2×10^{-7} cc/s for ICV ≥ 0.4 cc 4h at 2.0 atm Limit: 1×10^{-7} cc/s for ICV ≥ 0.4 cc Gross Leak – Integrated Circuits MIL-STD-883 Method 1014 cond. C1 (fluorocarbon gross leak) 5 Torr vacuum for 30 minutes minimum followed by pressurization of the devices immersed in mineral oil and subsequent immersion in another mineral oil at Ta = 125°C – Discrete Devices MIL-STD-750 Method 1071 cond. C (fluorocarbon gross leak) 0.5 Torr vacuum for 1h, except for ICV ≥ 0.1 cc, followed by pressurization of the devices immersed in mineral oil at: 4.1 atm for 2h ICV ≤ 0.1 cc or 5.1 atm for 2h ICV ≥ 0.1 cc and subsequent immersion in mineral oil at Ta = 125°C

In-process control during assembly process (cont'd)

PROCESS STEPS	TESTS	DESCRIPTION
18 (cont.d)	LID TORQUE CONTROL	Ceramic packages only MIL-STD-883 Method 2024 (e.g. ≥ 60 Kg x cm for seal area values between 1.41 and 1.73 cm ²)
19	TRIM & FORM AND LEAD FINISH	<ul style="list-style-type: none"> - Trim & Form not for Metal Can packages - Dimensions, thickness and contamination control - Solderability control: Aging as per page 51 215 \pm 5°C for 3 \pm 0.5 sec. (SMD only) 235 \pm 5°C for 2 \pm 0.5 sec. 245 \pm 5°C for 5 \pm 0.5 sec.
20	INTERNAL WATER VAPOR CONTENT CONTROL	Dew Point method MIL-STD-883 Method 1018 procedure 3 5000 ppm max (dew point temperature less than - 15°C) Ceramic packages only
21	HIGH IMPACT SHOCK	Metal Can packages only (except T03) 20000 g minimum; t = 25 μ .sec. minimum; Y1 axis only
22	FINAL BAKE	For SMD only (according to internal specifications)
23	RAW LINE INSPECTION	<p>External Visual</p> <ul style="list-style-type: none"> - Integrated Circuits MIL-STD-883 Method 2009; CECC 90000 - Discrete Devices MIL-STD-750 Method 2071; CECC 50000 <p>Note: at this step some reliability tests (pressure pot, temperature cycling, life test etc.) are performed as a monitor, generally on a weekly basis, to have fast feedback on process behaviour (Real Time Control Tests)</p>
25	GROUP A INSPECTION	See page 56
26	GROUPS B, C AND D TESTS	Performed on the product family representative types (by rotation); the results are extended to all the other devices of the same family according to the structure similarity concept
28	PACKING AND DOCUMENTATION INSPECTION	<p>Inspection for:</p> <ul style="list-style-type: none"> - right quantity - right type - right boxing - right labelling - right documentation - various

RELIABILITY REPORT

GROUP A INSPECTION - FINISHED PRODUCT ACCEPTANCE

ICs and Discrete devices

SUBGROUP	PARAMETERS	MINIMUM SAMPLE SIZE	ACCEPTANCE NUMBER
A1	Visual and mechanical inspection	315	0
A2+A3+A4	Cumulative electrical and inoperative mechanical failures	315	0

Notes

- This product acceptance is valid for standard production, for agreed customer programs other sampling plans can be applied
- Specified temperature ranges according to SGS-THOMSON databooks

PPM (RESULTS AND TARGETS)

As a consequence of its quality improvement programmes SGS-THOMSON has continually improved outgoing quality and is pursuing ambitious quality targets.

PPM values and targets for cumulative electrical failures* (inoperative mechanical included)

CMOS	1986	1987	1988	1989	1990	1991
	75	60	40	30	20	10

* Values referred to the end of each year.

GROUPS B, C AND D TESTS

Integrated circuits - Groups B, C and D tests

Every week or every three months on raw line and/or finished products

SUBGROUP	TEST PROCEDURE	MIL-STD-883 METHOD	CECC 98000 METHOD	SGS-THOMSON TEST CONDITIONS	PACKAGE			MINIMUM SAMPLE SIZE	ACCEPTANCE NUMBER (C)	NOTES (1)
					METAL	CERAMIC	PLASTIC			
1	Physical dimension	2016	4.3	Data Sheet Drawing	x	x	x	2	0	
2	Resistance to solvents	2015	4.4	1 minute immersion in solvent solution followed by 10 strokes with a hard brush as per MIL-STD method (the procedure shall be repeated 3 times)	x	x	x	4	0	
3	Solderability	2003	4.6.10 Cond1	215 ±5°C 3 ±0.5sec. 235 ±5°C 2 ±0.5sec. 245 ±5°C 5 ±0.5sec.	- x x	- x x	x x x	22	0	2
4	Operating Life Test or Intermittent Life Test (for Power devices) end point electrical parameters	1005 -	4.8 -	1000 h according to detail spec 5000 Cycles as per device spec.	x -	x -	x x	45	0	3
5	Temperature cycling Constant acceleration Seal - fine - gross	1010 2001 1014	4.6.8 4.6.7 4.6.9	10 cycles Ta = -65°C to + 150°C 30000 g see page 38	x x x	x x x	- - x	22	0	4
6	Pressure pot end point electrical parameters	-	-	Ta = 121°C, 2 atm, 240 h min. as per device spec.	- -	- -	x x	22	0	
7	HAST (Highly Accelerated Stress Test) end point electrical parameters	-	4.6.3 Cond2	130°C/85%RH with bias t=150h according to detail specification as per device spec.	- -	- -	x x	22	0	

Notes

- 1) Sample can be increased according to LTPD table, till c=2
- 2) Aging of 8h in steam vapor or 16h at 155°C Soldering temperature of 215°C for SMD only
- 3) Ta such to have Tj=Tj max
- 4) 20000g for packages with cavity perimeter of 5cm or more and/or with a mass of 5 grams or more

RELIABILITY REPORT

Integrated circuits - Groups B, C and D tests

Every six months on raw line and/or finished products

SUBGROUP	TEST PROCEDURE	MIL-STD-883 METHOD	CECC 90000 METHOD	SGS-THOMSON TEST CONDITIONS	PACKAGE			MINIMUM SAMPLE SIZE	ACCEPTANCE NUMBER (C)	NOTES (I)
					METAL	CERAMIC	PLASTIC			
1	Lead integrity	2004	4 6 12 (1)	Tensile test (as per CECC 90000) Lead Fatigue Cond B2 - wire leads: a force of 0 229 ± 0 014 Kg for three 90 ± 5° arcs on each lead bending cycle 2 to 5 sec - dual-in-line and power moulded packages the leads shall be bent 3 times simultaneously for at least 15° permanent bend, returning then to the original position Solder pad adhesion Cond D a force of 0.299 Kg mm to each solder pad for 30sec minimum	x	-	-	22	0	2
	Seal - fine - gross		4 6 12 (2)		1014	4 6 9	-			
2	Thermal shock	1011	4 6 8	Cond B, 15 shocks, Ta = -55 to +125°C Cond C; 100 cycles Ta = -65 to +150°C	x	x	-	22	0	4
	Temperature cycling	1010	4 6 8		x	x	x			
	Moisture resistance	1004	4 6 3	Lead bend conditioning followed by 10 cycles of 24h, Ta = 25°C to 65°C RH = 80% to 100%, one 3h cycle at Ta = -10°C see page 54	x	x	-			
	Seal - fine - gross	1014	4 6 9	x	x	-				
	Visual examination	1004 1010	-	without appraisal of marking	x	x	-			
	end point electrical parameters			as per device spec	x	x	x			
3	Mechanical shock	2002	4 6 4	Cond B, 1500g, 0.5 msec, 5 blows in each of the 6 orientations; not operating Cond A, 20g, 3 orientations, f = 20 to 2000 cps, four 4 minutes cycles, 48 minutes total, not operating	x	x	-	22	0	5
	Vibration, variable frequency	2007	4 6 5		x	x	-			
	Constant accelerations	2001	4 6 7	Cond E; 3000g; Y1 orientation only	x	x	-			
	Seal - fine - gross	1014	4 6 9	see page 54	x	x	-			
	Visual examination	1010 1011	-	as per device spec	x	x	-			
4	Salt atmosphere	1009	4 6 14	Cond A, 10 to 50 gr of NaCl per m ² for 24 h at Ta= 35°C min see page 54	x	x	x	22	0	
	Seal - fine - gross	1014	4 6 9		x	x	-			
	Visual examination	1009	4 6 14		x	x	x			
5	Humidity test	-	4 6 3 Cond 1	85°C/85% RH with bias t = 1000h according to detail specification as per device spec	-	-	x	45	0	
	end point electrical parameters				-	-	x			
6	Internal water-vapor content	1018	-	Dew point method procedure 3 (5000 ppm max)	x	x	-	3 5	0 1	6
7	Lid Torque	2024	-	see page 54	-	x	-	22	0	7

Notes

- 1) Sample can be increased according to LTPD table, till c=2
- 2) Not for SMD
- 3) Leadless chip carrier only
- 4) For plastic packages Ta = -65/-40°C according to device type
- 5) 2000g for packages with cavity perimeter of 5cm or more and/or with a mass of 5 grams or more
- 6) Test three devices If one fails, test two additional devices with no failure
- 7) Applied only to packages which use glass-frit seal to lead the frame lead or package body (i.e. wherever frit seal establishes hermeticity or package integrity)

LPS - RESULTS SUMMARY

Test	Condition	Plastic				Ceramic				S.O. Package			
		1989		1990		1989		1990		1989		1990	
		SS	REJ	SS	REJ	SS	REJ	SS	REJ	SS	REJ	SS	REJ
HIGH TEMPERATURE BIAS	1000 hrs	1971	0	1809	0	620	0	675	0	738	0	756	0
	2000 hrs	540	0	513	0	135	0			198	0	216	0
TEMPERATURE HUMIDITY BIAS	1000 hrs	1951	0	1890	0	-	-	-	-	738	0	918	0
	2000 hrs	513	0	378	0					180	0	216	0
PRESSURE COOKER	168 hrs	2125	0	1830	0	-	-	-	-	795	0	810	0
	336 hrs	675	0	630	0					275	0	270	0
THERMAL SHOCKS	200 cyc	1425	0	1950	0	450	0	375	0	150	0	125	0
THERMAL CYCLES	200 cyc 1000 cyc	1070	0	1110	0	570	0	540	0	580	0	630	0
ENVIRONMENTAL SEQUENCE		-	-	-	-	1325	0	1275	0	-	-	-	-
MECHANICAL SEQUENCE		-	-	-	-	1325	0	1275	0	-	-	-	-
RESISTANCE TO SOLVENT		475	1	425	1	350	0	325	0	425	1	375	0
SOLDERABILITY		475	0	425	0	350	0	325	0	425	2	375	1
LEAD INTEGRITY		475	0	425	0	350	0	325	0				
HAST	96 hrs	175	0	225	0	-	-	-	-	100	0	125	0
	240 hrs	100	0	100	0					50	0	75	0

FAILURE RATE EVALUATION (AT 60% CONFIDENCE LEVEL)

Package	Device x Hours	Fail	Failure Rate	
			FIT *	
			125°C	55°C
PLASTIC	3.78 x 10 ⁶	0	242	0.5
CERAMIC	1.32 x 10 ⁶	0	693	1.4
S.O. PACKAGE	1.49 x 10 ⁶	0	613	1.3

* FIT = Failure in Time. Number of failures/10⁹ Hours of operation (or 10⁻⁹). The activation energy, from analysis, was chosen as 0.7 eV based on our tests results: the failure rate at lower operating temperature can be extrapolated from the Arrhenius plot.

The actual junction temperature should be used; it can be computed using the relationship

$$T_j = T_A + (P \times \theta_{JA})$$

Where T_j = Junction temperature
 T_A = Ambient temperature
 θ_{JA} = Junction to ambient thermal resistance (typically 100°C/watt for a 16 pin DIP)
 P = Power actual consumption

DATASHEETS



NOR GATE

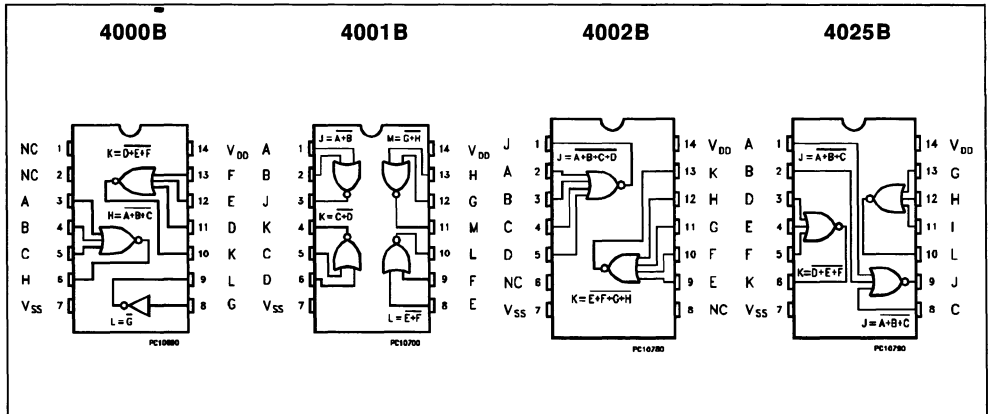
4000B—DUAL 3 INPUT PLUS INVERTER
4001B—QUAD 2 INPUT
4002B—DUAL 4 INPUT
4025B TRIPLE 3 INPUT

- PROPAGATION DELAY TIME = 60 ns (typ.) AT $C_L = 50$ pF, $V_{DD} = 10$ V
- BUFFERED INPUTS AND OUTPUTS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20 V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25 °C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

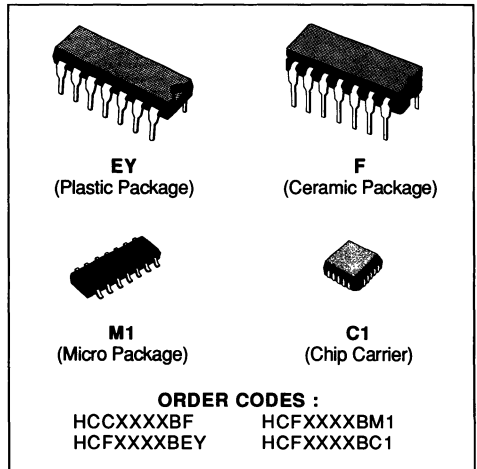
DESCRIPTION

The **HCC4000B**, **HCC4001B**, **HCC4002B** and **HCC4025B** (extended temperature range) and **HCF4000B**, **HCF4001B**, **HCF4002B** and **HCF4025B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in line plastic or ceramic package and plastic micropackage.

PIN CONNECTIONS



The **HCC/HCF4000B**, **HCC/HCF4001B**, **HCC/HCF4002B** and **HCC/HCF4025B** nor gate provide the system designer with direct implementation of the nor function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

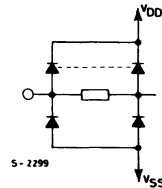
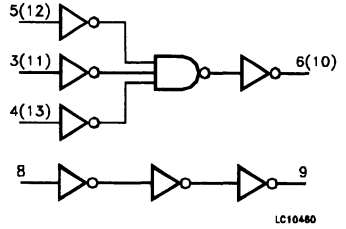
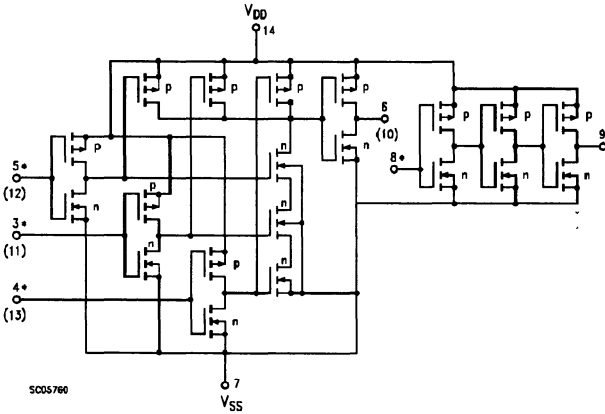
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

SCHEMATIC AND LOGIC DIAGRAMS

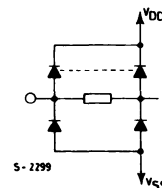
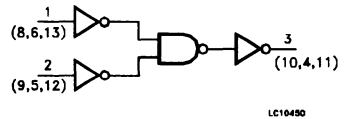
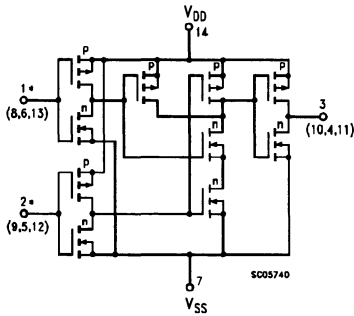
4000B



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

INVERTER AND 1 OF 2 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR SECOND GATE)

4001 B

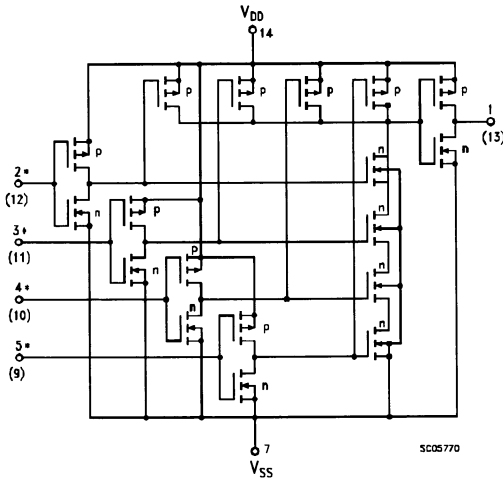


ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

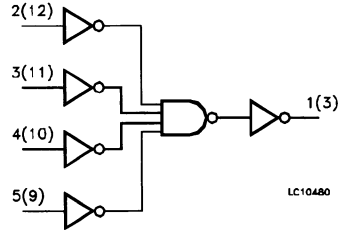
1 OF 4 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR OTHER GATE)

SCHEMATIC AND LOGIC DIAGRAMS (continued)

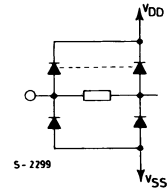
4002B



1 OF 2 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR SE-
COND GATE)

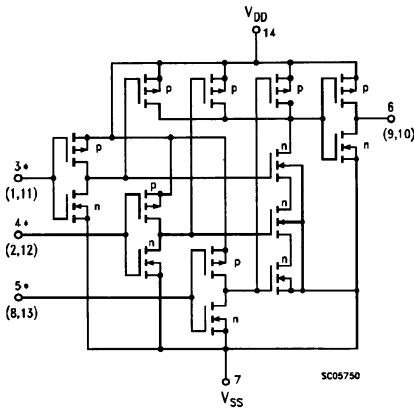


LC10480

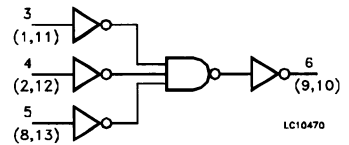


ALL INPUTS ARE PROTECTED BY
COS/MOS PROTECTION NETWORK

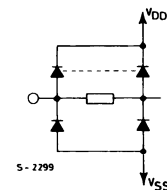
4025B



INVERTER AND 1 OF 3 GATES (NUMBERS IN PARANTHESES ARE
THERMINAL FOR OTHER GATES)



LC10470



ALL INPUTS ARE PROTECTED BY
COS/MOS PROTECTION NETWORK

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
	HCF Types	0/5			5		1		0.01	1		7.5		
		0/10			10		2		0.01	2		15		
		0/15			15		4		0.01	4		30		
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _i	Input Capacitance			Any Input					5	7.5			pF	

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

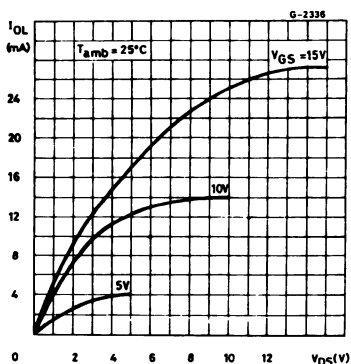
* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

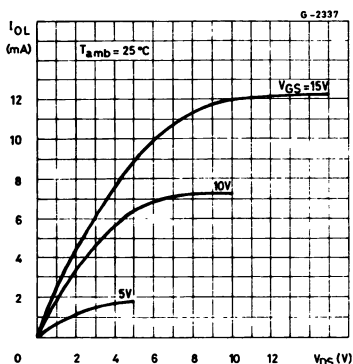
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			5		45	90	
t_{THL} t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

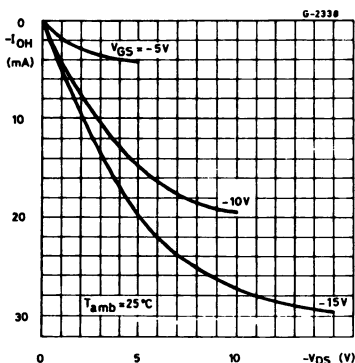
Typical Output Low (sink) Current Characteristics



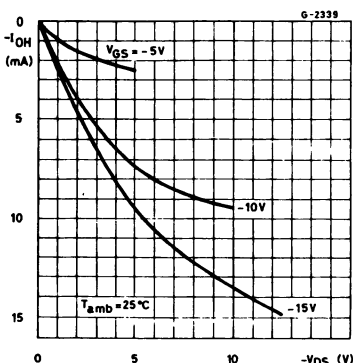
Minimum Output Low (sink) Current Characteristics



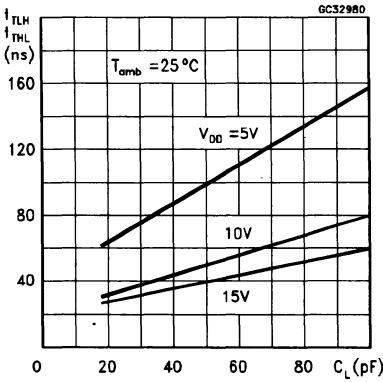
Typical Output High (source) Current Characteristics



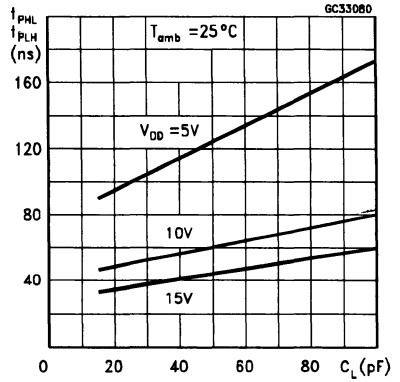
Minimum Output High (source) Current Characteristics



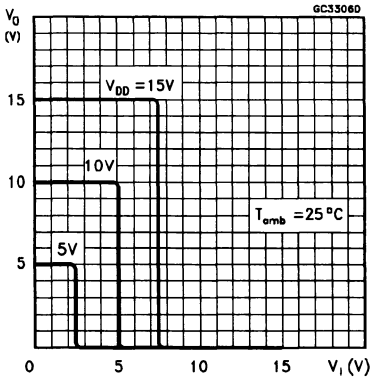
Typical Transition Time vs Load Capacitance



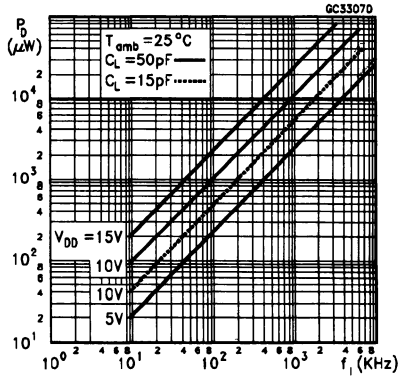
Typical Propagation Delay Time vs Load Capacitance



Typical Voltage Transfer Characteristics as a Function of Temperature

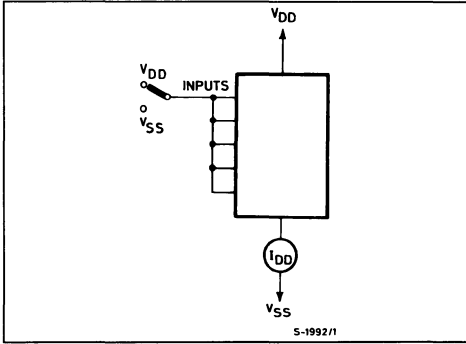


Typical Power Dissipation Per Gate vs Frequency

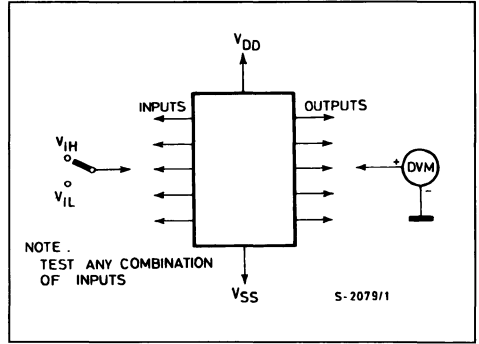


TEST CIRCUITS

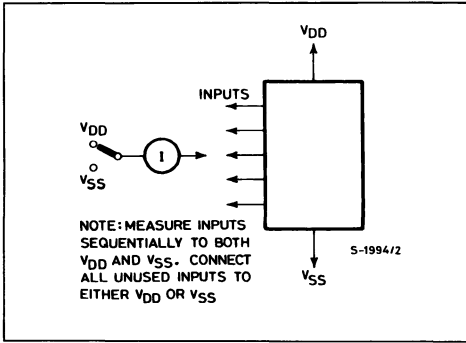
Quiescent Device Current.



Noise Immunity.



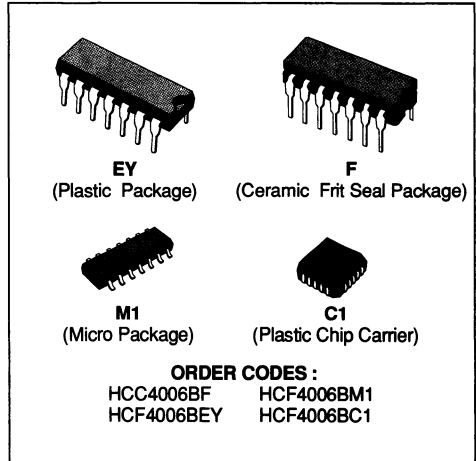
Input Leakage Current.





18-STAGE STATIC SHIFT REGISTER

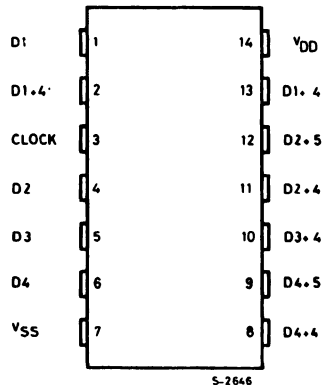
- PERMANENT REGISTER STORAGE WITH CLOCK LINE "HIGH" OR "LOW" ... NO INFORMATION RECIRCULATION REQUIRED
- FULLY STATIC OPERATION
- SHIFTING RATES UP TO 12MHz @ 10V (typ.)
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25 °C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATING
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



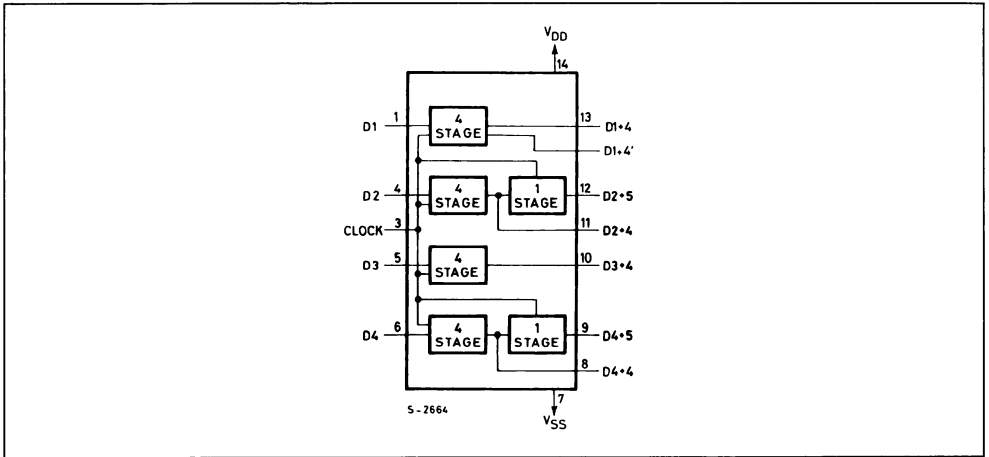
DESCRIPTION

The **HCC4006B** (extended temperature range) and the **HCF4006B** (standard temperature range), are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micro package. The types are comprised of 4 separate "shift register" sections ; two sections of four stages and two sections of five stages with an output tap at the fourth stage. Each section has an independent "single rail" data path. A common clock signal is used for all stages. Data is shifted to the next stage on negative-going transitions of the clock. Through appropriate connections of inputs and outputs, multiple register sections of 4, 5, 8, and 9 stages or single register sections of 10, 12, 13, 14, 16, 17 and 18 can be implemented using one **HCC/HCF4006B** package. Longer shift register sections can be assembled by using more than one **HCC/HCF4006B**. To facilitate cascading stages when clock rise and fall times are slow, an optional output (D₁ + 4') that is delayed one-half clock-cycle, is provided (see truth table for output from pin 2).

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

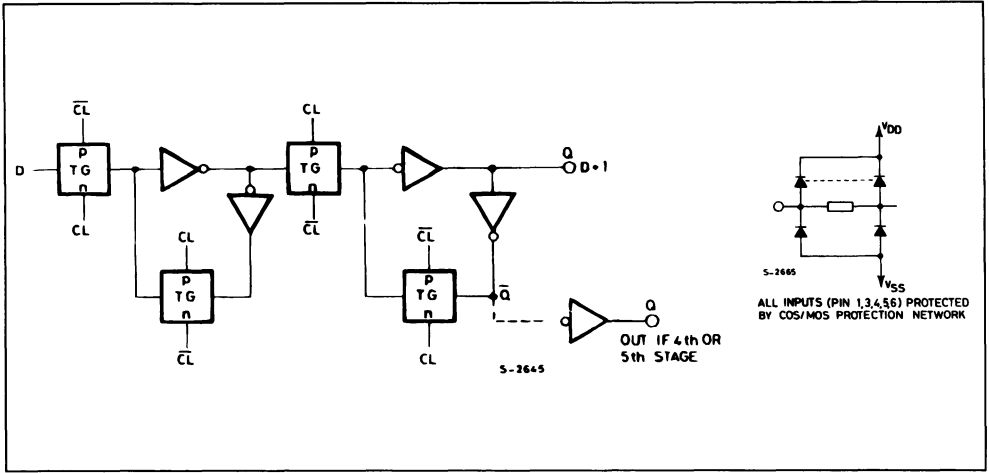
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAM AND TRUTH TABLES (one register stage)



TRUTH TABLE FOR OUTPUT FROM PIN 2

$D_1 + 4$	CL^Δ	$D_1 + 4'$
0	\uparrow	0
1	\uparrow	1
X	\downarrow	NC

TRUTH TABLE FOR SHIFT REGISTER STAGE

D	CL^Δ	$D + 1$
0	\downarrow	0
1	\downarrow	1
X	\uparrow	NC

1 = HIGH
 0 = LOW
 NC = NO CHANGE

X = DON'T CARE
 Δ = LEVEL CHANGE

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{Low} *		25°			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5	0.04	5		150	μ A	
			0/10			10		10	0.04	10		300		
			0/15			15		20	0.04	20		600		
			0/20			20		100	0.08	100		3000		
	HCF Types	0/5			5		20	0.04	20		150			
		0/10			10		40	0.04	40		300			
		0/15			15		80	0.04	80		600			
V _{OH}	Output High Voltage	0/5		<1	5	4.95		4.95			4.95	V		
		0/10		<1	10	9.95		9.95			9.95			
		0/15		<1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		<1	5		0.05			0.05	0.05	V		
		10/0		<1	10		0.05			0.05	0.05			
		15/0		<1	15		0.05			0.05	0.05			
V _{IH}	Input High Voltage	0.5/4.5	<1	5	3.5			3.5			3.5	V		
		1/9	<1	10	7			7			7			
		1.5/13.5	<1	15	11			11			11			
V _{IL}	Input Low Voltage	4.5/0.5	<1	5		1.5				1.5	1.5	V		
		9/1	<1	10		3				3	3			
		13.5/1.5	<1	15		4				4	4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5	5	-2		-1.6	-3.2		-1.15	mA		
			0/5	4.6	5	-0.64		-0.51	-1		-0.36			
			0/10	9.5	10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5	15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5	5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6	5	-0.52		-0.44	-1		-0.36			
			0/10	9.5	10	-1.3		-1.1	-2.6		-0.9			
0/15	13.5	15	-3.6		-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4	5	0.64		0.51	1		0.36	mA		
			0/10	0.5	10	1.6		1.3	2.6		0.9			
			0/15	1.5	15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4	5	0.52		0.44	1		0.36			
			0/10	0.5	10	1.3		1.1	2.6		0.9			
			0/15	1.5	15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1		
C _i	Input Capacitance		Any Input					5	7.5			pF		

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.

* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

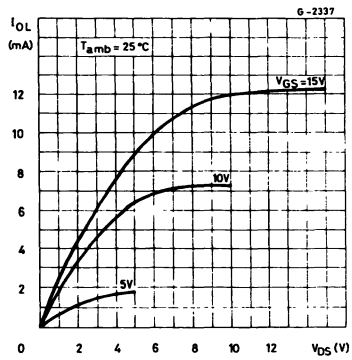
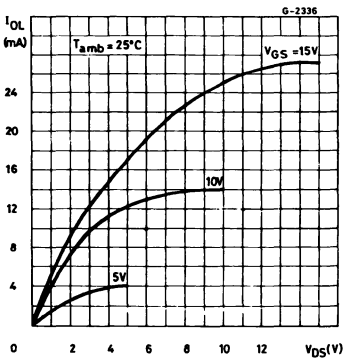
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		200		ns
			10		100		
			15		80		
t_{THL} , t_{TLH}	Transition Time		5		100		ns
			10		50		
			15		40		
t_w	Clock Pulse Width		5		100		ns
			10		45		
			15		30		
t_r , t_f	Clock Input Rise or Fall Time*		5		15		μs
			10		15		
			15		15		
t_{setup}	Data Setup Time		5		50		ns
			10		25		
			15		20		
f_{max}	Maximum Clock Input Frequency		5		5		MHz
			10		12		
			15		16		

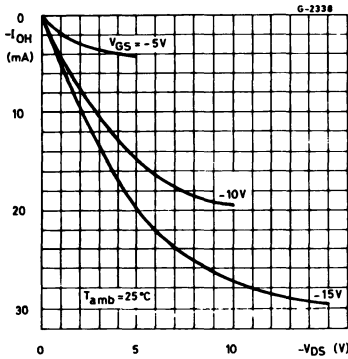
* If more than unit is cascaded t_{CL} should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.

Typical Output Low (sink) Current Characteristics.

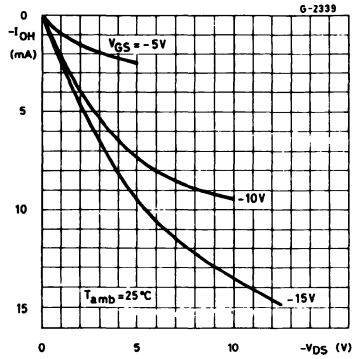
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

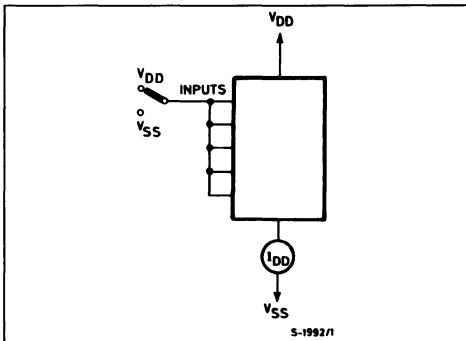


Minimum Output High (source) Current Characteristics.

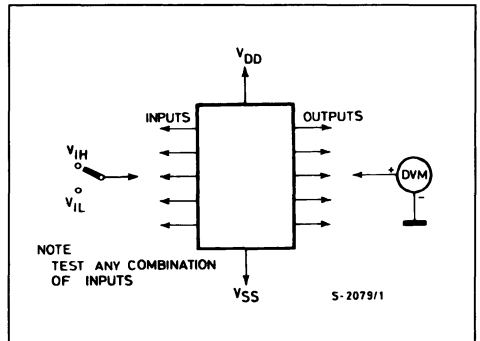


TEST CIRCUITS

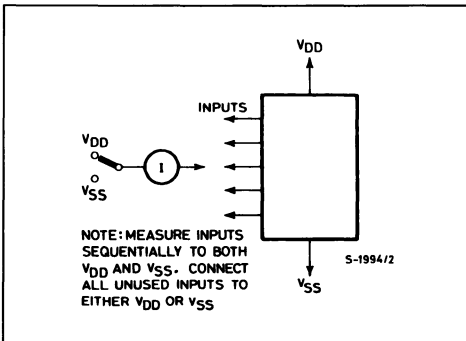
Quiescent Device Current.



Input Voltage.

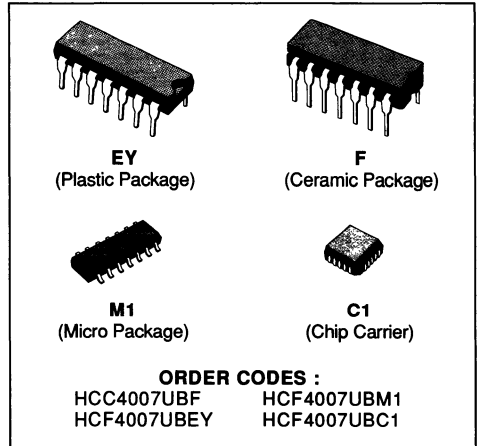


Input Current.



DUAL COMPLEMENTARY PAIR PLUS INVERTER

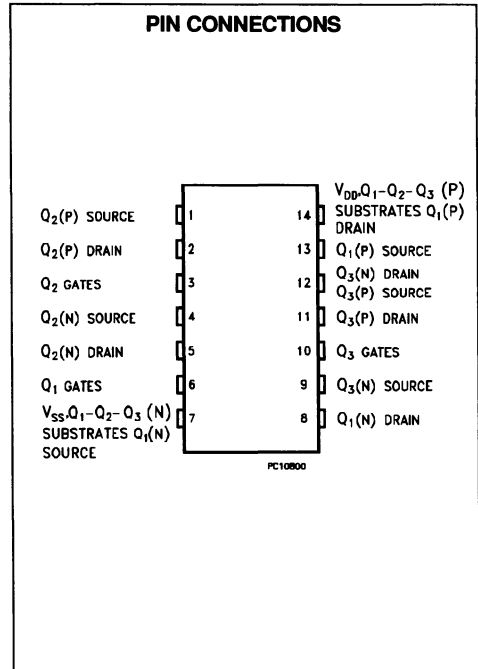
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- MEDIUM SPEED OPERATION t_{pHL} , $t_{pLH} = 30\text{ns}$ (typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



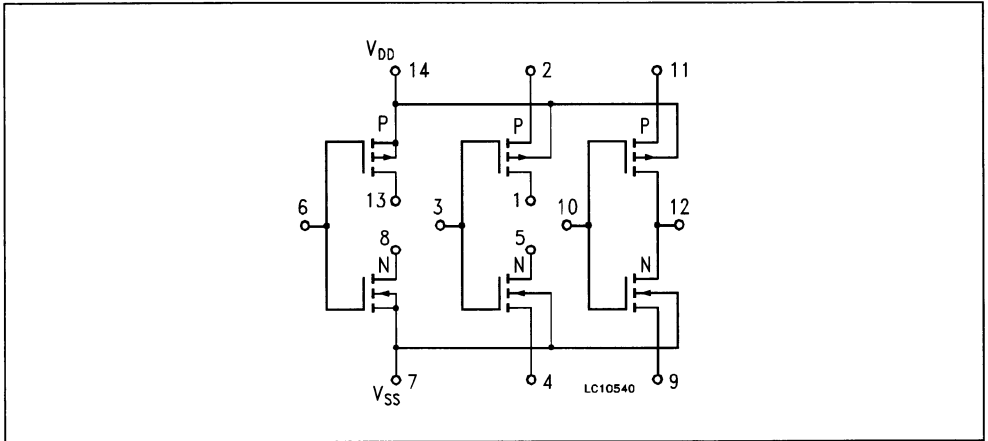
DESCRIPTION

The HCC4007UB is a monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The HCC4007UB type is comprised of three n-channel and three p-channel enhancement type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in typical applications. More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the various configurations listed.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V V
V_I	Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package Temperature Range	200 100	mW mW
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$

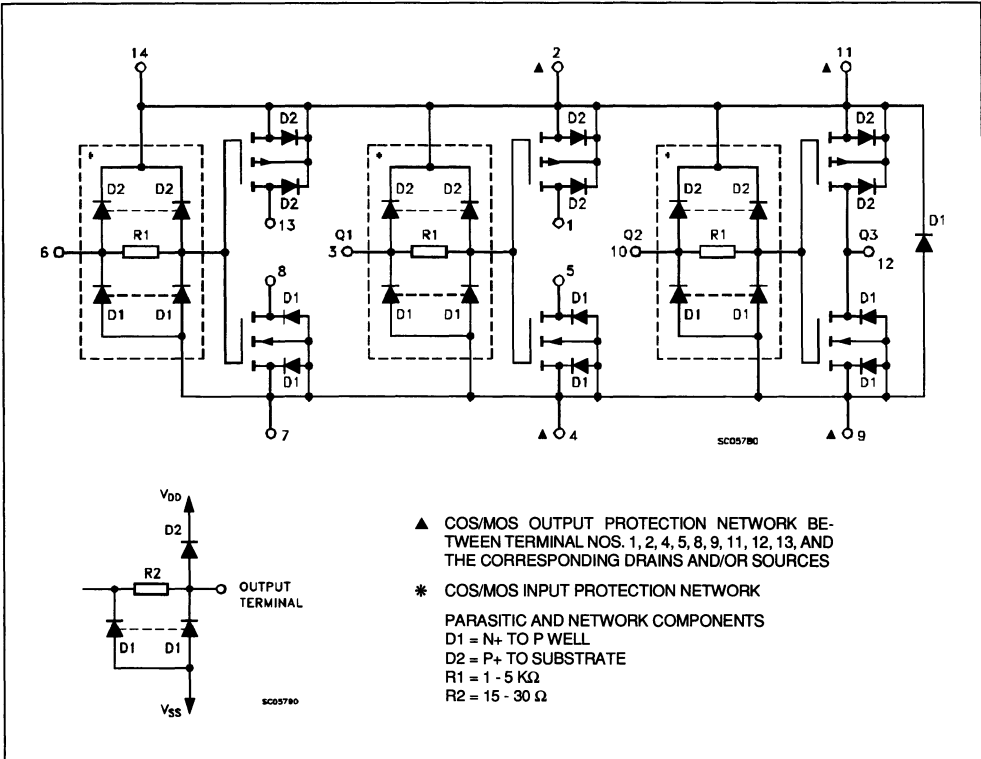
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$

SCHEMATIC DIAGRAM (showing input, output and parasitic diodes)



▲ COS/MOS OUTPUT PROTECTION NETWORK BETWEEN TERMINAL NOS. 1, 2, 4, 5, 8, 9, 11, 12, 13, AND THE CORRESPONDING DRAINS AND/OR SOURCES

* COS/MOS INPUT PROTECTION NETWORK

- PARASITIC AND NETWORK COMPONENTS
- D1 = N+ TO P WELL
- D2 = P+ TO SUBSTRATE
- R1 = 1 - 5 KΩ
- R2 = 15 - 30 Ω

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25	0.01	0.25		7.5	μ A	
			0/10			10		0.5	0.01	0.5		15		
			0/15			15		1	0.01	1		30		
			0/20			20		5	0.02	5		150		
		HCF Types	0/5			5		1	0.01	1		7.5		
			0/10			10		2	0.01	2		15		
0/15				15		4	0.01	4		30				
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95		V		
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V		
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	4		4			4		V		
		1/9	< 1	10	8		8			8				
		1.5/13.5	< 1	15	12.5		12.5			12.5				
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1			1		1	V		
		9/1	< 1	10		2			2		2			
		13.5/1.5	< 1	15		2.5			2.5		2.5			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5	5	-2		-1.6	-3.2		-1.15	mA		
			0/5	4.6	5	-0.64		-0.51	-1		-0.36			
			0/10	9.5	10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5	15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5	5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6	5	-0.52		-0.44	-1		-0.36			
0/10	9.5		10	-1.3		-1.1	-2.6		-0.9					
0/15	13.5	15	-3.6		-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4	5	0.64		0.51	1		0.36	mA		
			0/10	0.5	10	1.6		1.3	2.6		0.9			
			0/15	1.5	15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4	5	0.52		0.44	1		0.36			
			0/10	0.5	10	1.3		1.1	2.6		0.9			
			0/15	1.5	15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1	\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A		
		HCF Types	0/15		15		\pm 0.3	\pm 10 ⁻⁵	\pm 0.3		\pm 1			
C _I	Input Capacitance		Any Input					5	7.5			pF		

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

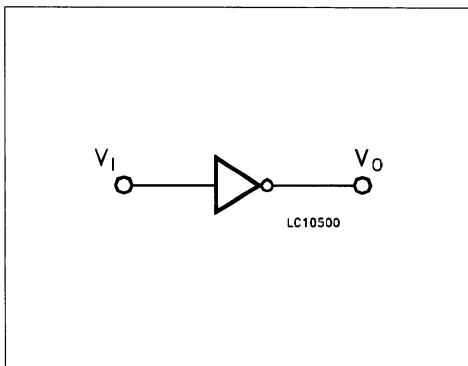
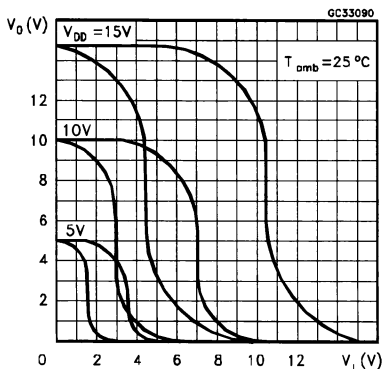
* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

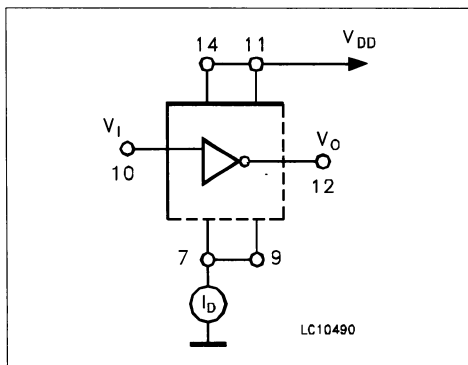
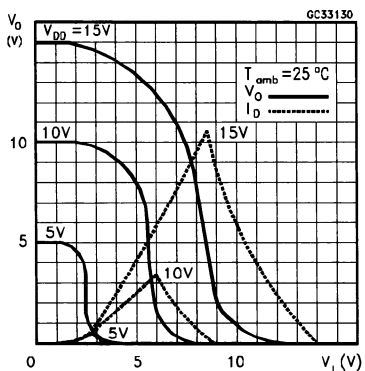
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time		5		55	110	ns
			10		30	60	
			15		25	50	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

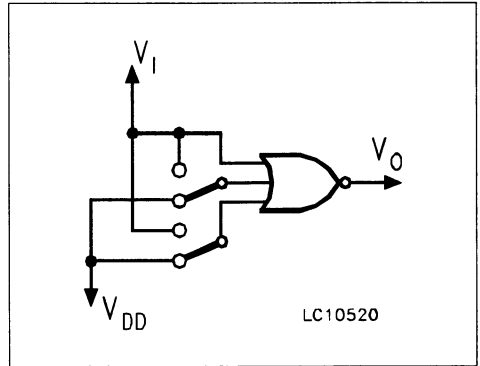
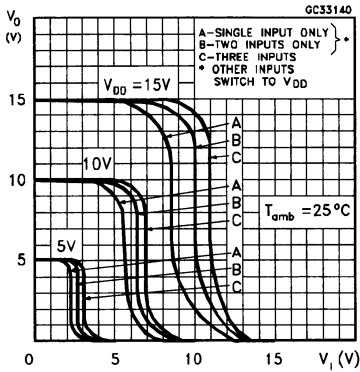
Minimum and Maximum Voltage Transfer Characteristics for Inverter and test Circuit



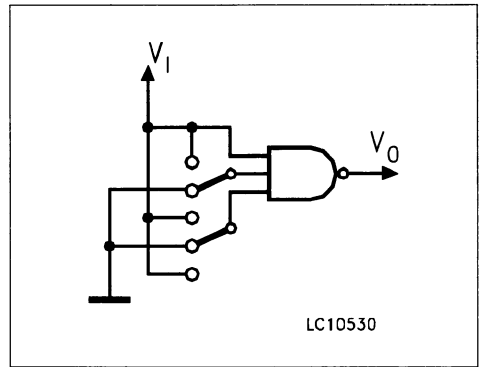
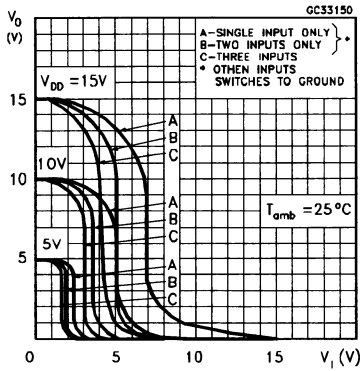
Typical Current and Voltage Transfer Characteristics for Inverter and Test Circuit



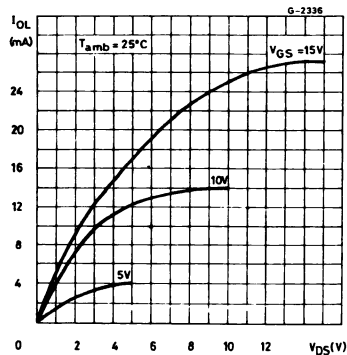
Typical Voltage Transfer Characteristics for NAND Gate and Test Circuit



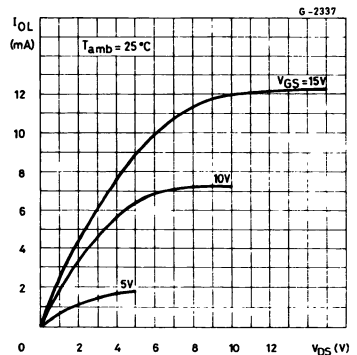
Typical Voltage Transfer Characteristics for NOR Gate and Test Circuit



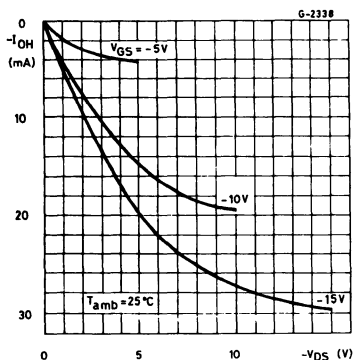
Typical Output Low (Sink) Current Characteristics



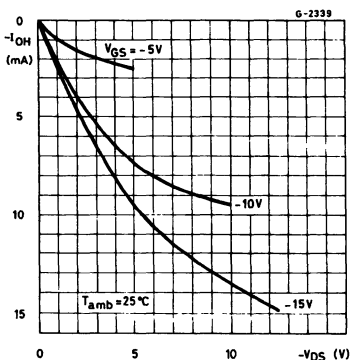
Minimum Output Low (Sink) Current Characteristics



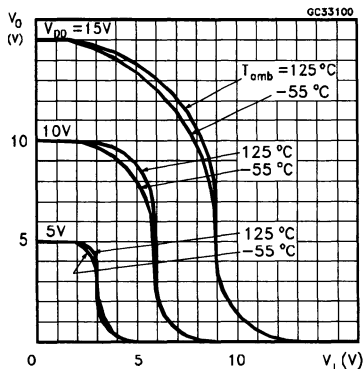
Typical Output High (Source) Current Characteristics



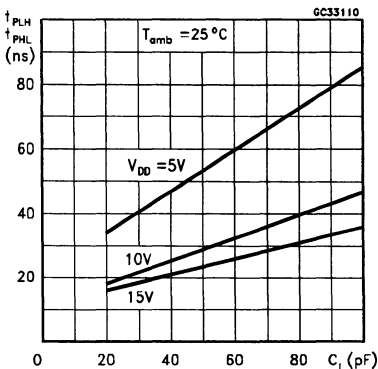
Minimum Output High (Source) Current Characteristics



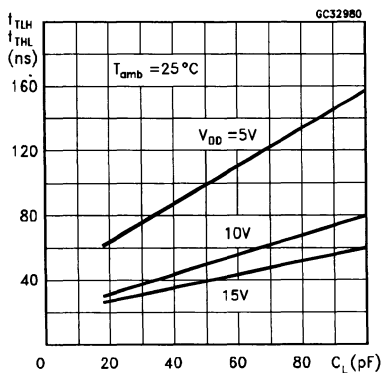
Typical Voltage Transfer Characteristics as a Function of Temperature



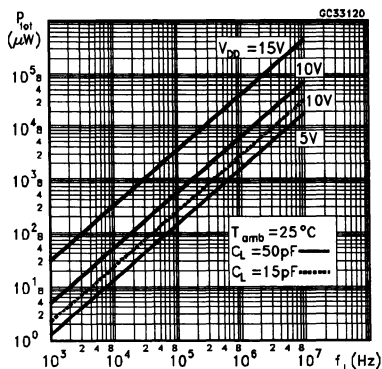
Typical Propagation Delay Time vs. Load Capacitance



Typical Transition Time vs. Load Capacitance

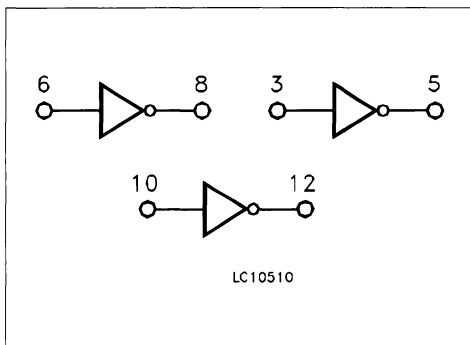


Typical Dissipation Per Gate vs. Frequency Characteristics

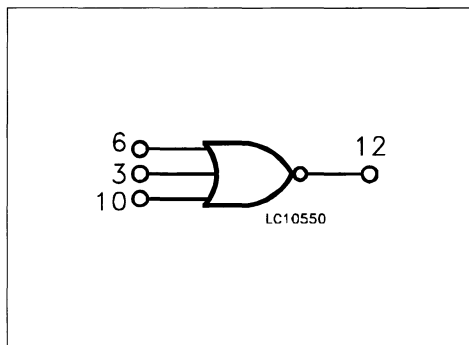


TYPICAL APPLICATIONS (Sample COS/MOS logic circuit arrangements using type 4007UB)

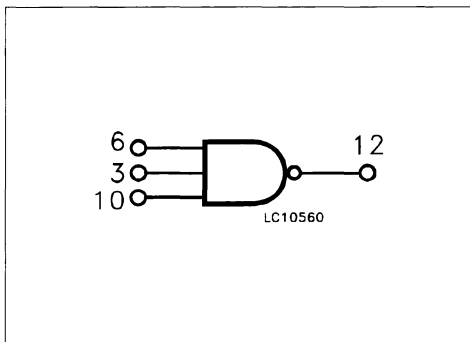
Triple Inverters: (14, 2, 11); (8, 13); (1, 5); (4, 7, 9).



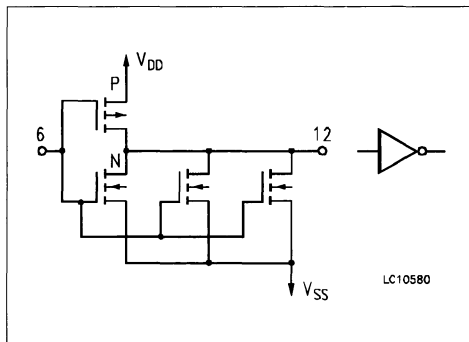
3-Input NOR Gate: (13, 2); (1, 11); (12, 5, 8); (4, 7, 9).



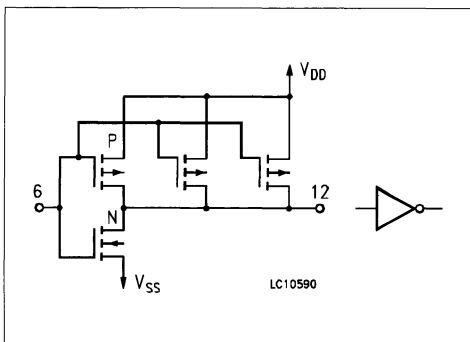
3-Input NAND Gate: (1, 12, 13); (2, 14, 11); (4, 8); (5, 9).



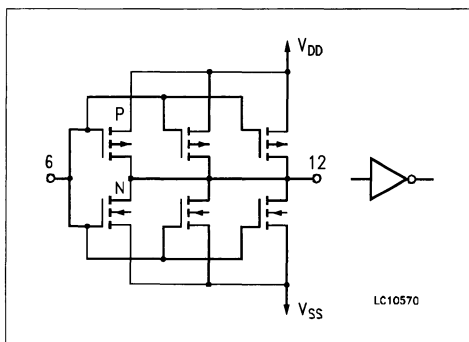
High Sink Current Driver: (6, 3, 10); (8, 5, 12); (11, 14); (4, 7, 9).



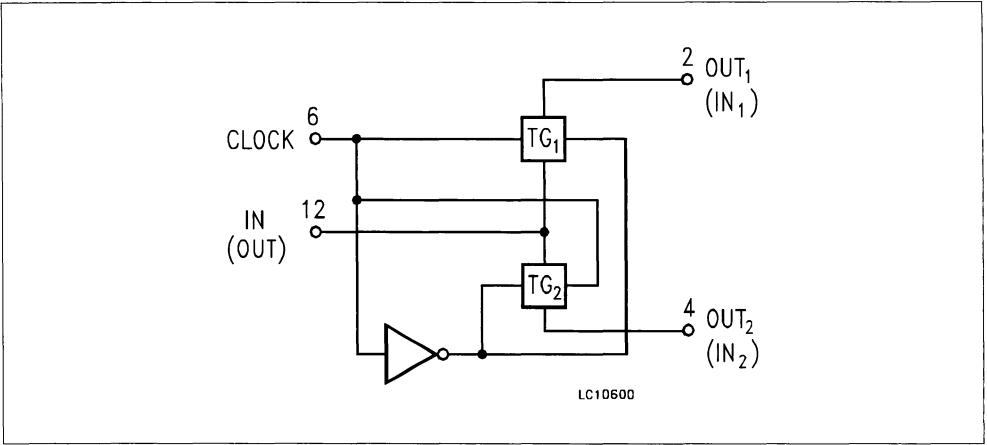
High Source Current Driver: (6, 3, 10); (13, 1, 12); (14, 2, 11); (7, 9).



High Sink and Source Current Driver: (6, 3, 10); (14, 2, 11); (7, 4, 9); (13, 8, 1, 5, 12).

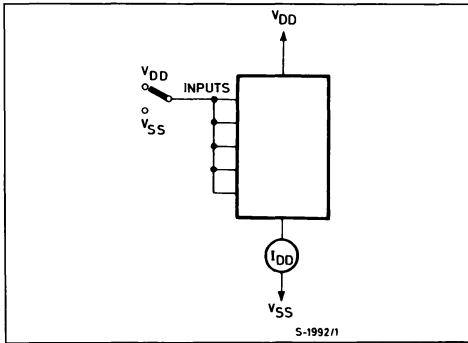


Dual Bidirectional Transmission Gating: (1, 5, 12); (2, 9); (11, 4); (8, 13, 10); (6, 3).

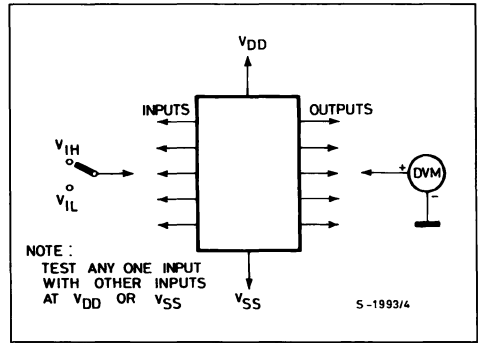


TEST CIRCUIT

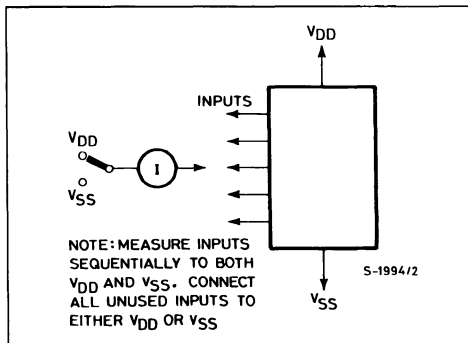
Quiescent Device Current.



Input Voltage.

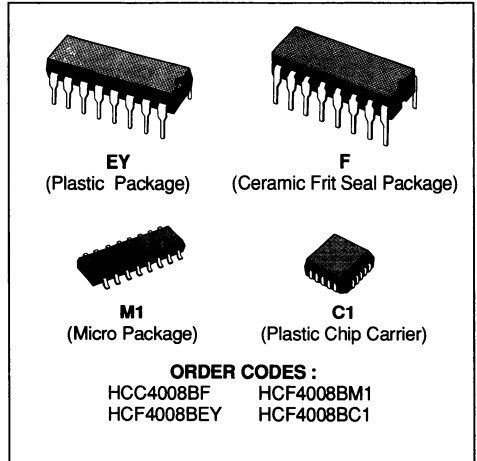


Input Leakage Current.



4-BIT FULL ADDER WITH PARALLEL CARRY OUTPUT

- 4 SUM OUTPUTS PLUS PARALLEL LOOK-AHEAD CARRY-OUTPUT
- HIGH-SPEED OPERATION-SUM IN-TO-SUM OUT 160ns (typ.) : CARRY IN-TO-CARRY OUT 50ns (typ.) AT $V_{DD} = 10V$, $C_L = 50pF$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATING
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



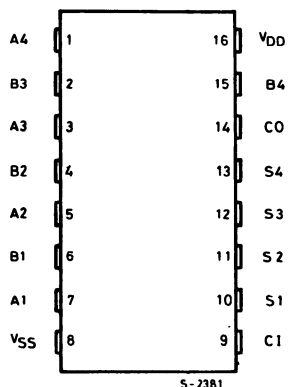
DESCRIPTION

The **HCC4008B** (extended temperature range) and **HCF4008B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4008B** types consist of four full adder stages with fast look ahead carry provision from stage to stage. Circuitry is included to provide a fast "parallel-carry-out" to permit high-speed operation in arithmetic sections using several HCC/HCF 4008B's.

HCC/HCF4008B inputs include the four sets of bits to be added, A_1 to A_4 and B_1 to B_4 , in addition to the "Carry In" bit from a previous section. **HCC/HCF4008B** outputs include the four sum bits, S_1 to S_4 . In addition to the high speed "parallel-carry-out" which may be utilized at a succeeding **HCC/HCF4008B** section.

PIN CONNECTIONS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{Tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for $T_{Op} =$ Full Package-temperature Range	100	mW
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T_{Stg}	Storage Temperature	- 65 to + 150	°C

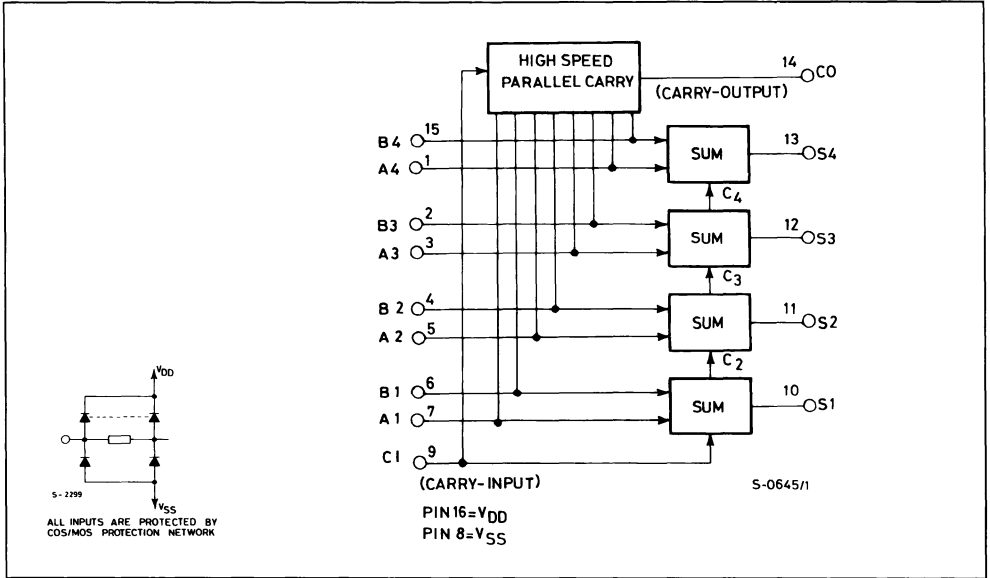
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

A _i	B _i	C _i	C _O	SUM
0	0	0	0	0
1	0	0	0	1
0	1	0	0	1
1	1	0	1	0
0	0	1	0	1
1	0	1	1	0
0	1	1	1	0
1	1	1	1	1

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

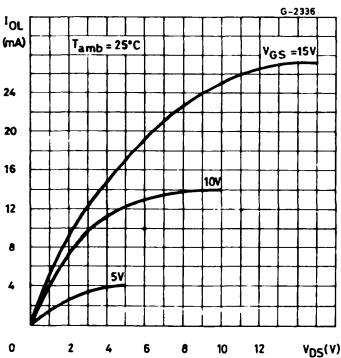
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

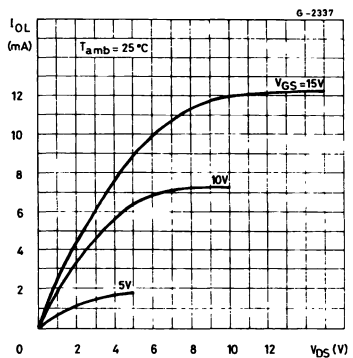
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter		Test Conditions	Value			Unit			
				V_{DD} (V)	Min.	Typ.		Max.		
t_{PLH} , t_{PHL}	Propagation Delay Time	Sum In to Sum Out		5		400	800	ns		
				10		160	320			
				15		115	230			
				5		370	740			
				10		155	310			
				15		115	230			
		Carry In to Sum Out				5			200	400
						10			90	180
						15			65	130
						5			100	200
						10			50	100
						15			40	80
Sum In to Carry Out			5		100	200				
			10		50	100				
			15		40	80				
			5		100	200				
			10		50	100				
			15		40	80				
t_{THL} , t_{TLH}	Transition Time			5		100	200	ns		
				10		50	100			
				15		40	80			

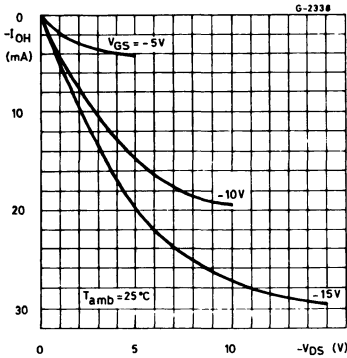
Typical Output Low (sink) Current.



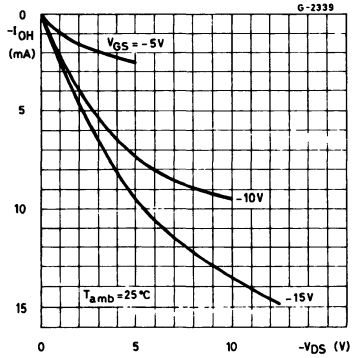
Minimum Output Low (sink) Current Characteristics.



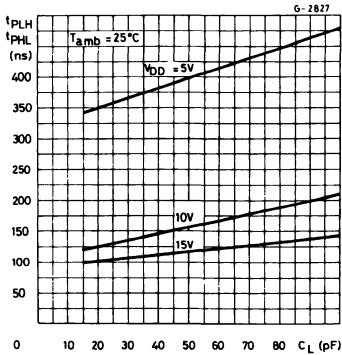
Typical Output High (source) Current Characteristics.



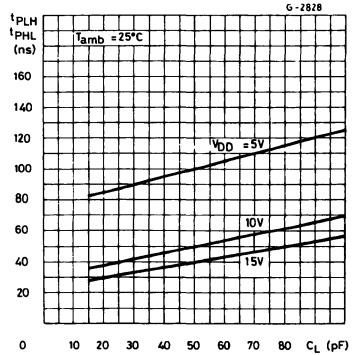
Minimum Output High (source) Current Characteristics.



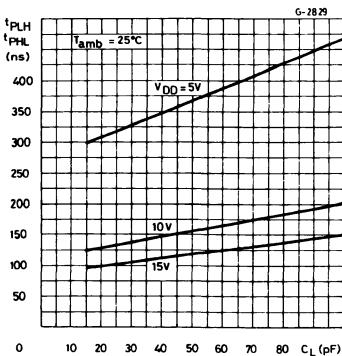
Typical Sum-in to Sum Out Propagation Delay vs. Load Capacitance.



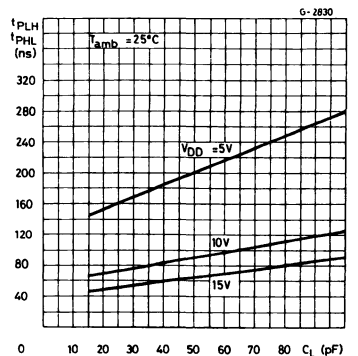
Typical Carry-in to Carry-Out Propagation Delay vs. Load Capacitance.



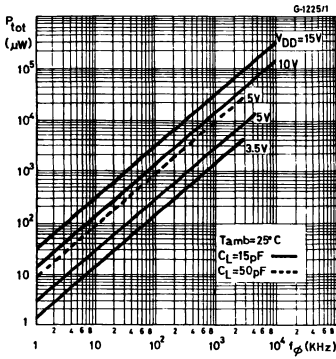
Typical Carry-in to Sum Out Propagation Delay Time vs. Load Capacitance.



Typical Sum-in to Carry-Out Propagation Delay Time vs. Load Capacitance.

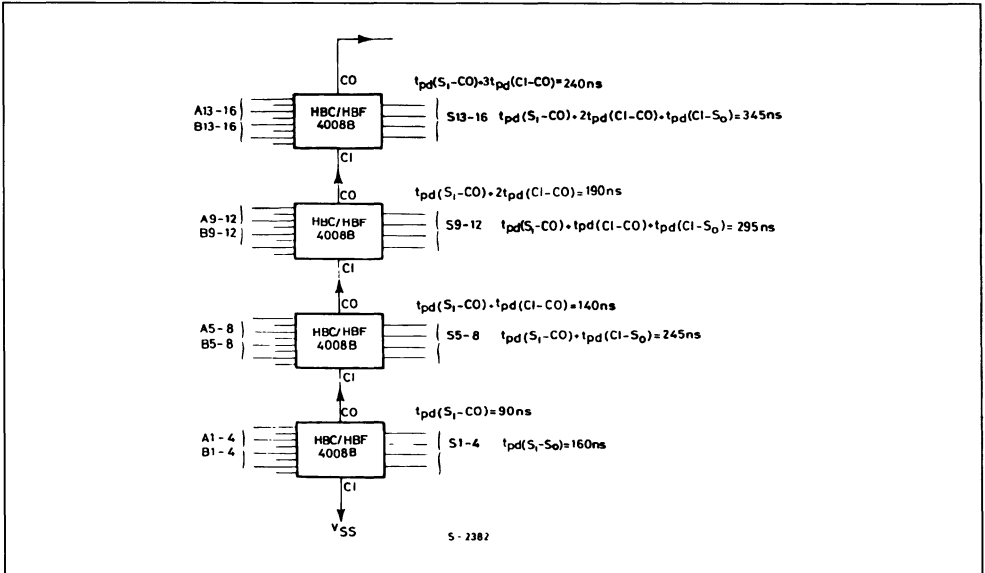


Typical Dynamic Power Dissipation/Package vs. Frequency.



TYPICAL APPLICATIONS

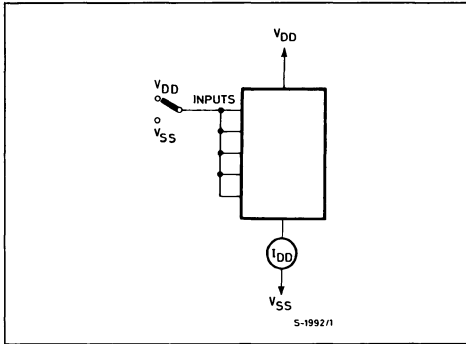
SPEED CHARACTERISTICS OF A 16-BIT ADDER.



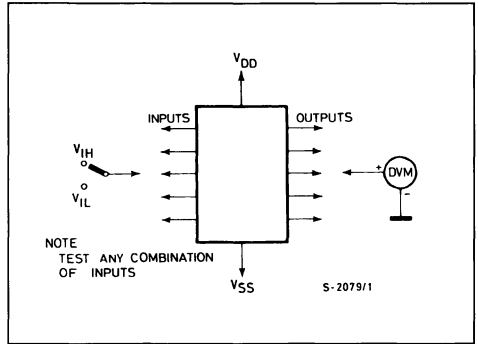
Notes : All "A" and "B" input bits occur at $t = 0$.
 All sums settled at $t = 345\text{ ns}$.
 $C_L = 50\text{ pF}$, $T_{amb} = 25^\circ\text{C}$, $V_{DD} - V_{SS} = 10\text{V}$.

TEST CIRCUITS

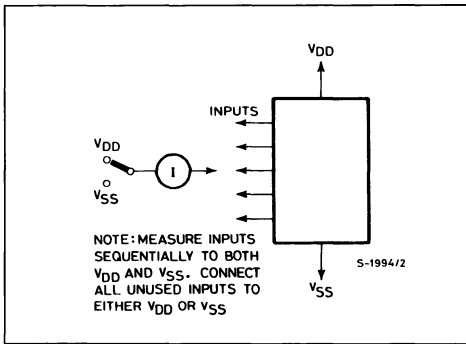
Quiescent Device Current.



Input Voltage.



Input Current.



HEX BUFFER/CONVERTERS

4009UB—INVERTING TYPE

4010B—NON INVERTING TYPE

- CMOS TO DTL/TTL HEX CONVERTER
- HIGH-TO-LOW LEVEL LOGIC CONVERSION
- MULTIPLEXER: 1-TO-6 OR 6-TO-1
- HIGH "SINK" AND "SOURCE" CURRENT CAPABILITY
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MAXIMUM INPUT CURRENT OF 100 μ A AT 18V OVER FULL
- PACKAGE AND TEMPERATURE RANGE; 100nA AT 18V AND 25°C
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

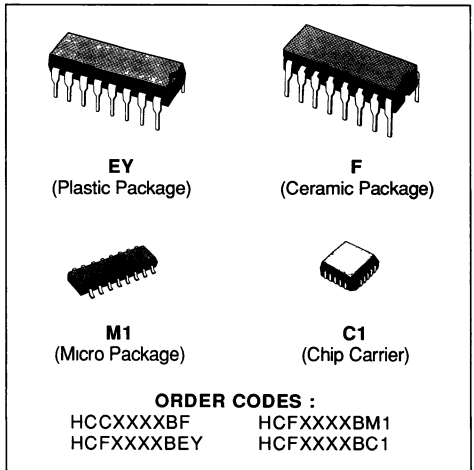
DESCRIPTION

The **HCC4009UB/4010B** (extended temperature range) and the **HCF4009UB/4010B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in line plastic or ceramic packages and plastic micropackage.

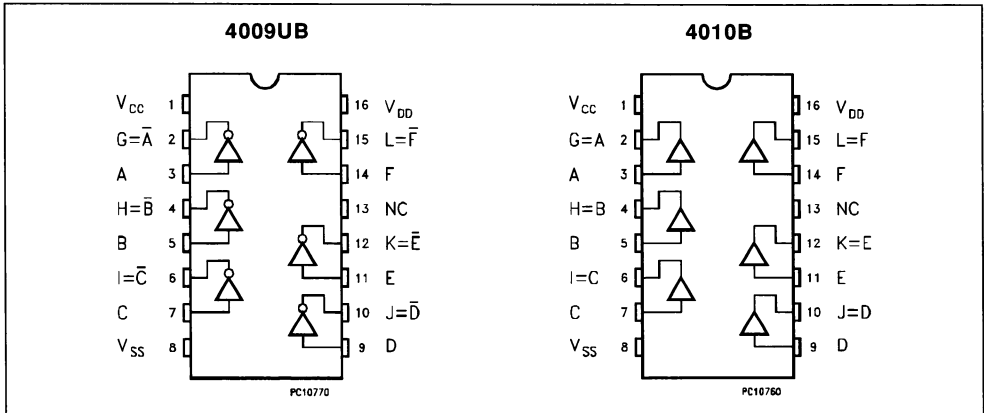
The **HCC/HCF4009UB/4010B** are inverting and

non-inverting Hex Buffer/Converters, respectively. Both devices can be used as CMOS to TTL or DTL logic-level converters, as current "sink" or "source" drivers or as multiplexer (1 to 6).

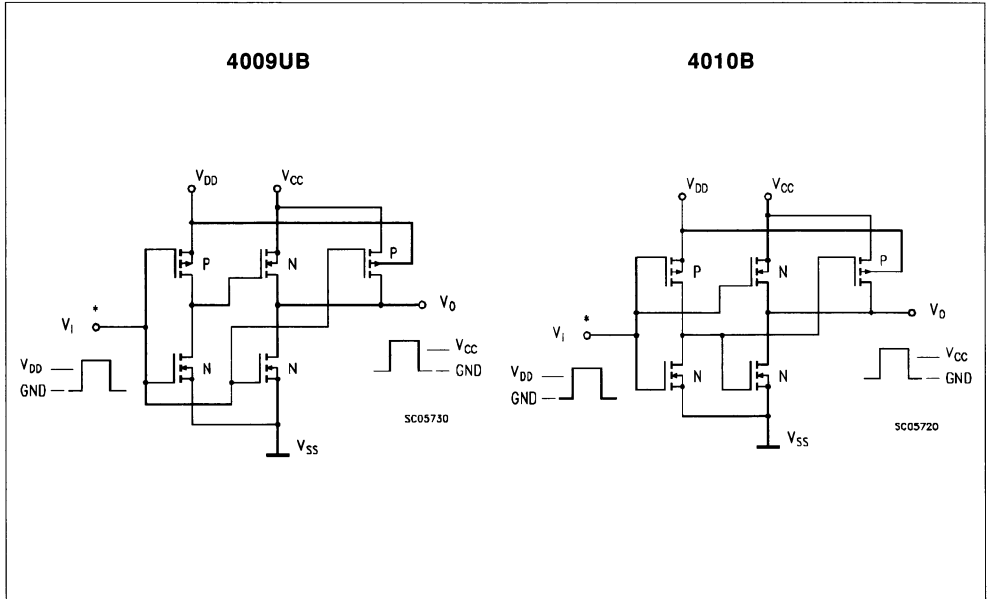
4049UB and **4050B** are preferred replacements for **4009UB** and **4010B**, respectively, in buffer applications.



PIN CONNECTIONS



SCHEMATIC DIAGRAM: COS/MOS TO DTL OR TTL CONVERTER (1 of 6 identical units)



Connect Vcc to DTL or TTL supply and VDD to COS/MOS supply

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

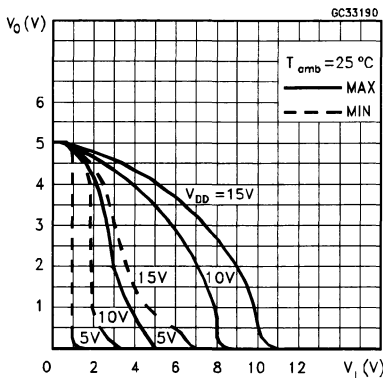
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1	0.02	1		30	μ A	
			0/10			10		2	0.02	2		60		
			0/15			15		4	0.02	4		120		
			0/20			20		20	0.04	20		600		
		HCF Types	0/5			5		4	0.02	4		30		
			0/10			10		8	0.02	8		60		
			0/15			15		16	0.02	16		120		
V _{OH}	Output High Voltage	0/5			5	4.95		4.95			4.95	V		
		0/10			10	9.95		9.95			9.95			
		0/15			15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0			5		0.05		0.05		0.05	V		
		10/0			10		0.05		0.05		0.05			
		15/0			15		0.05		0.05		0.05			
V _{IH}	Input High Voltage (4009UB)		0.5		5	4		4			4	V		
			1		10	8		8			8			
			1.5		15	12.5		12.5			12.5			
V _{IH}	Input High Voltage (4010B)		4.5		5	3.5		3.5			3.5	V		
			9		10	7		7			7			
			13.5		15	11		11			11			
V _{IL}	Input Low Voltage (4009UB)		4.5		5	1			1		1	V		
			9		10	2			2		2			
			13.5		15	2.5			2.5		2.5			
V _{IL}	Input Low Voltage (4010B)		0.5		5	1.5			1.5		1.5	V		
			1		10	3			3		3			
			1.5		15	4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-1	-0.8	-1.6		-0.58	mA		
			0/5	4.6		5	-0.25	-0.2	-0.4		-0.15			
			0/10	9.5		10	-0.55	-0.45	-0.9		-0.33			
			0/15	13.5		15	-1.65	-1.5	-3		-1.1			
		HCF Types	0/5	2.5		5	-0.9	-0.8	-1.6		-0.65			
			0/5	4.6		5	-0.23	-0.2	-0.4		-0.18			
			0/10	9.5		10	-0.5	-0.45	-0.9		-0.38			
0/15	13.5		15	-1.6	-1.5	-3		-1.25						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	3.75	3	4		2.1	mA		
			0/10	0.5		10	10	8	10		5.6			
			0/15	1.5		15	30	24	36		16			
		HCF Types	0/5	0.4		5	3.6	3	4		2.4			
			0/10	0.5		10	0.96	8	10		6.4			
			0/15	1.5		15	40	24	36		1.9			
I _{IH} , I _{IL}	Input Leakage Current	0/18			18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
C _I	Input Capacitance	4009UB		Any Input					15	22.6				
		4010B							5	7.5			pF	

* T_{Low} = -55 °C for HCC device; -40 °C for HCF device.* T_{High} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

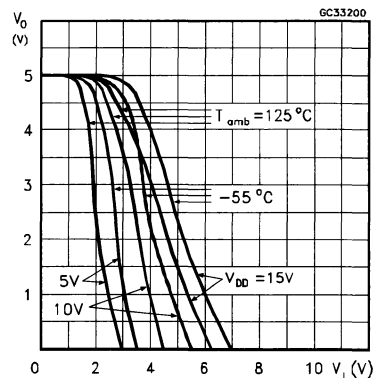
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Conditions			Value			Unit
		V_{DD} (V)	V_I (V)	V_{CC} (V)	Min.	Typ.	Max.	
t_{PLH}	Propagation Delay Time (4009UB)	5	5	5		70	140	ns
		10	10	10		40	80	
		10	10	5		35	70	
		15	15	15		30	60	
		15	15	5		30	60	
t_{PLH}	Propagation Delay Time (4010B)	5	5	5		100	200	ns
		10	10	10		50	100	
		10	10	5		50	100	
		15	15	15		35	70	
		15	15	5		35	70	
t_{PHL}	Propagation Delay Time (4009UB)	5	5	5		30	60	ns
		10	10	10		20	40	
		10	10	5		15	30	
		15	15	15		15	30	
		15	15	5		10	20	
t_{PHL}	Propagation Delay Time (4010B)	5	5	5		65	130	ns
		10	10	10		35	70	
		10	10	5		30	70	
		15	15	15		25	50	
		15	15	5		20	40	
t_{TLH}	Transition Time	5	5	5		150	350	ns
		10	10	10		75	150	
		15	15	15		55	110	
t_{THL}	Transition Time	5	5	5		35	70	ns
		10	10	10		20	40	
		15	15	15		15	30	

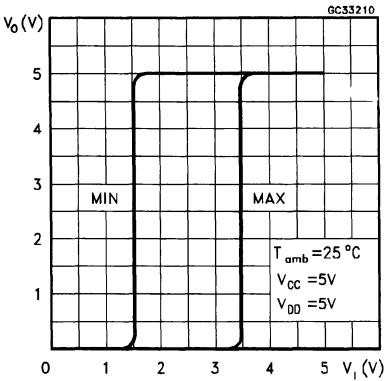
Minimum and Maximum Voltage Transfer Characteristics for 4009UB



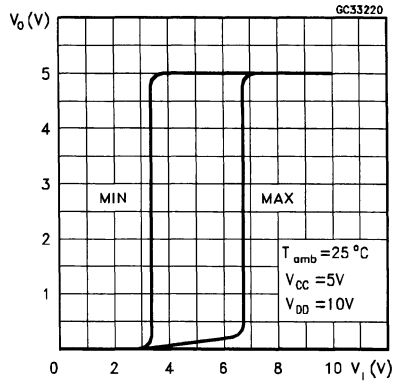
Typical Voltage Transfer Characteristics As a Function of Temperature for 4009UB



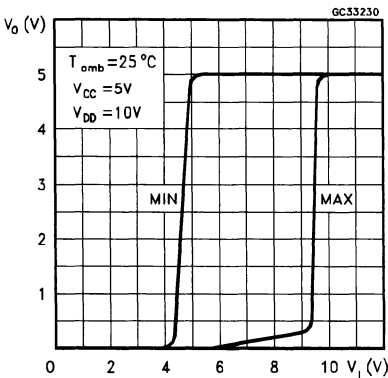
Minimum and Maximum Voltage Transfer Characteristics for 4010B



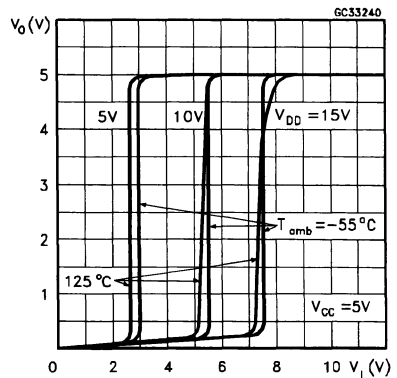
Minimum and Maximum Voltage Transfer Characteristics for 4010B



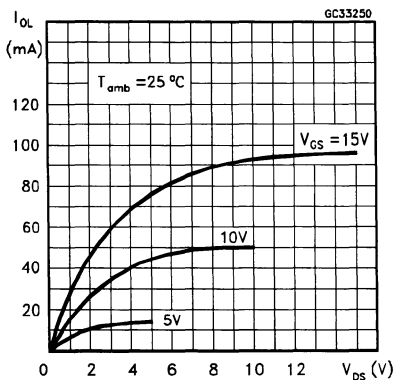
Minimum and Maximum Voltage Transfer Characteristics for 4010B



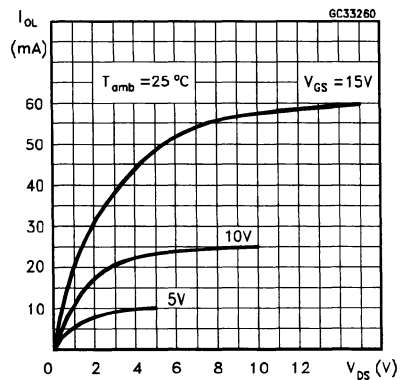
Typical Voltage Transfer Characteristics As a Function of Temperature for 4010B



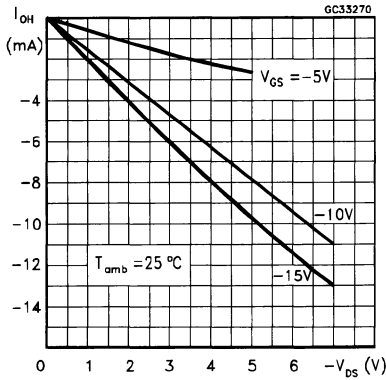
Typical Output Los (sink) Current Characteristics



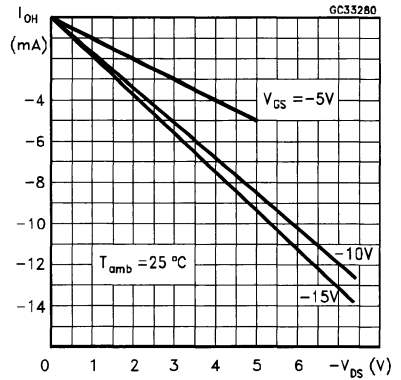
Minimum output Low (sink) Current Characteristics



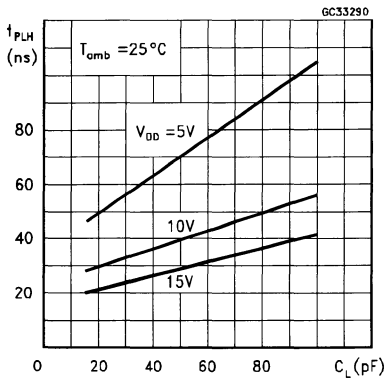
Typical Output High (source) Current Characteristics



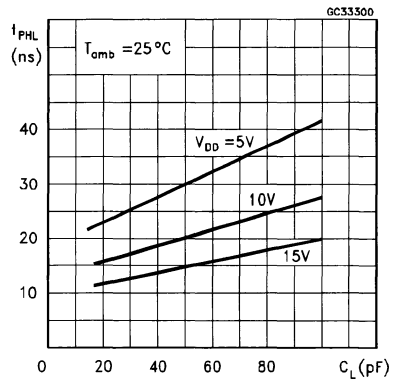
Minimum output High (source) Current Characteristics



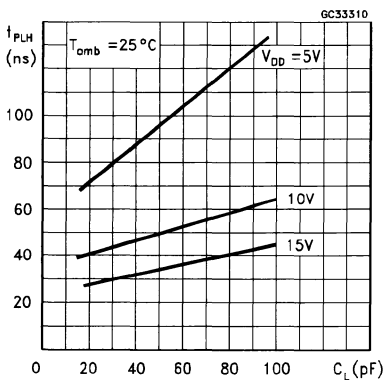
Typical Low to High Propagation Delay Time vs Load Capacitance for 4009UB



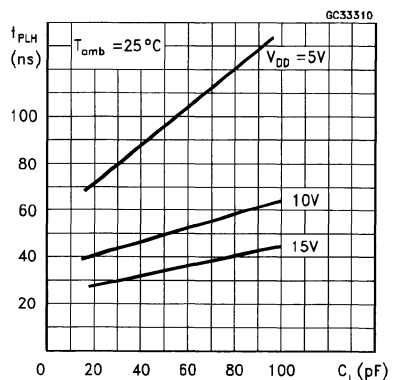
Typical High to Low Propagation Delay Time vs Load Capacitance for 4009UB



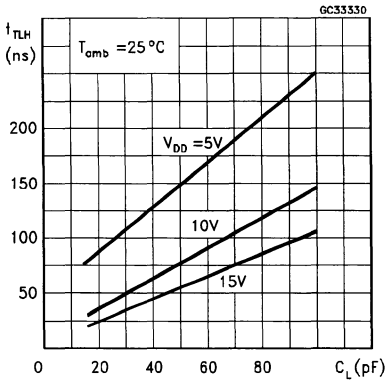
Typical Low to High Propagation Delay Time vs Load Capacitance for 4010B



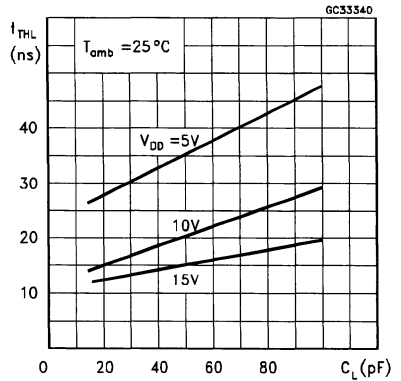
typical High to Low Propagation Delay Time vs Load Capacitance for 4010B



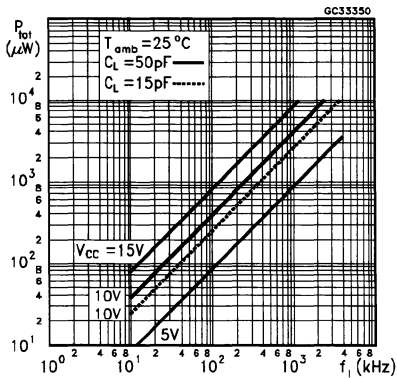
Typical Low to High Transition Time vs Load Capacitance



Typical High to Low Transition Time vs Load Capacitance

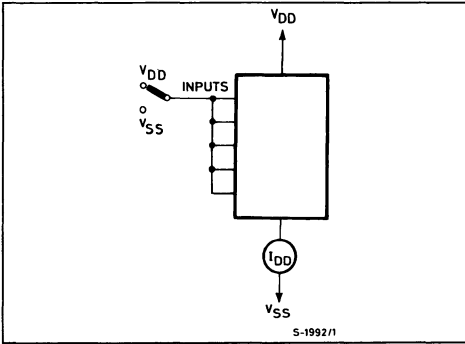


Typical Dissipation Characteristics

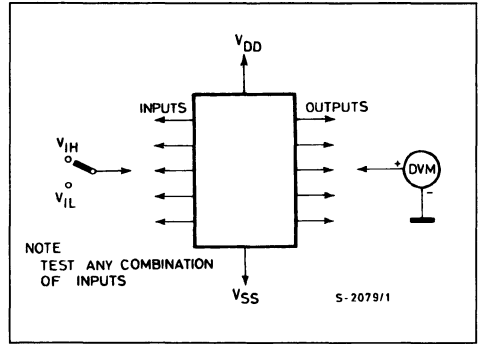


TEST CIRCUITS

Quiescent Device Current.

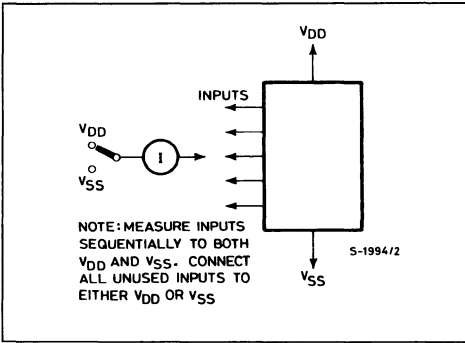


Noise Immunity.



NOTE
TEST ANY COMBINATION
OF INPUTS

Input Leakage Current.



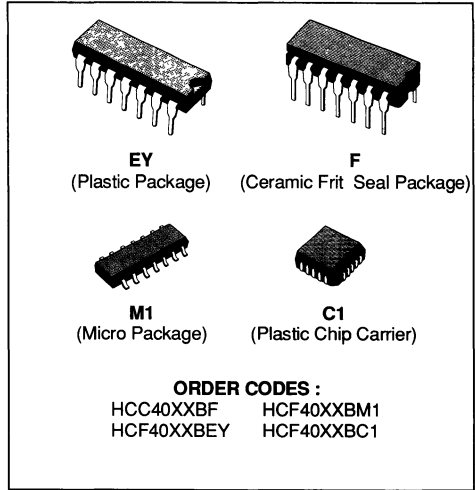
NOTE: MEASURE INPUTS
SEQUENTIALLY TO BOTH
V_{DD} AND V_{SS}. CONNECT
ALL UNUSED INPUTS TO
EITHER V_{DD} OR V_{SS}



NAND GATES

QUAD 2 INPUT HCC/HCF 4011B
DUAL 4 INPUT HCC/HCF 4012B
TRIPLE 3 INPUT HCC/HCF 4023B

- PROPAGATION DELAY TIME = 60ns (typ.) AT $C_L = 50\text{pF}$, $V_{DD} = 10\text{V}$
- BUFFERED INPUTS AND OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

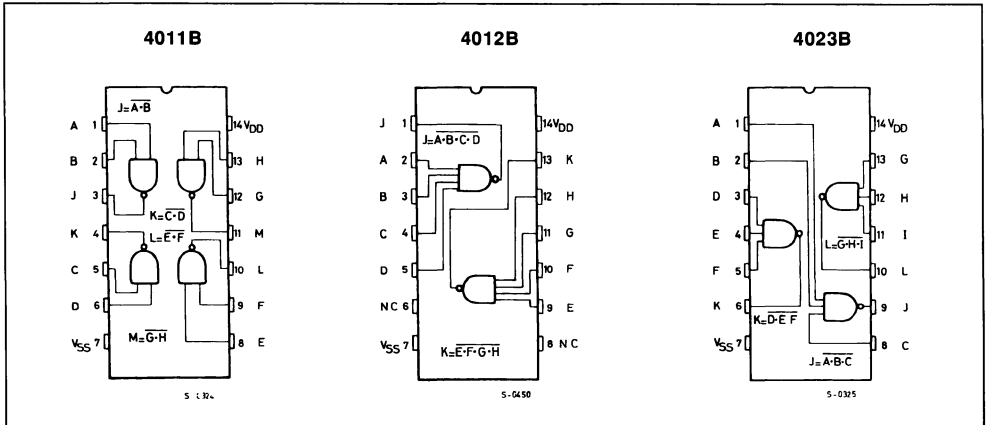


DESCRIPTION

The **HCC4011B**, **HCC4012B** and **HCC4023B** (extended temperature range) and **HCF4011B**, **HCF4012B** and **HCF4023B** (intermediate temperature range) are monolithic, integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4011B**, **HCC/HCF4012B** and **HCC/HCF4023B** NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.

PIN CONNECTIONS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

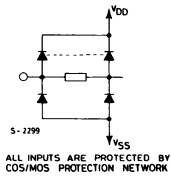
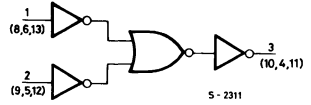
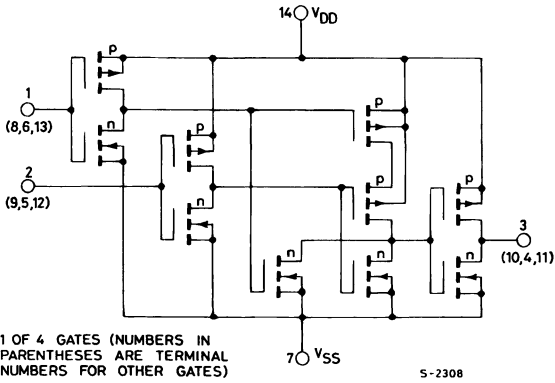
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

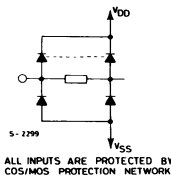
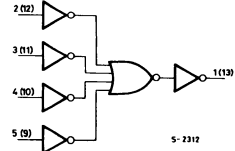
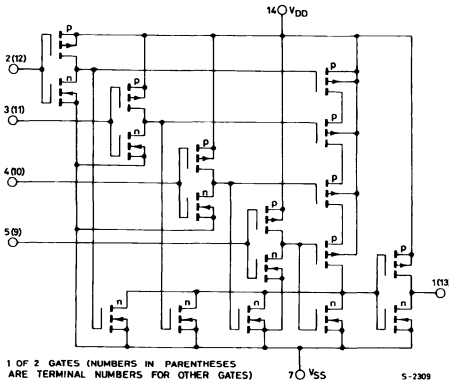
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

SCHEMATIC AND LOGIC DIAGRAMS

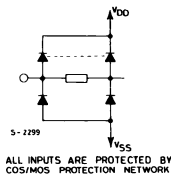
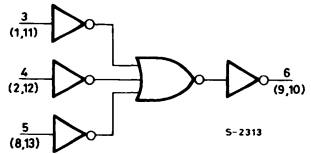
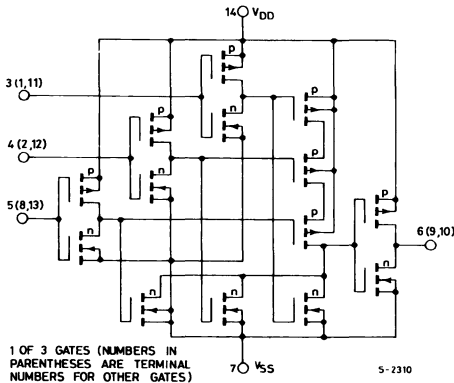
4011B



4012B



4023B



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15			15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1		
C _I	Input Capacitance			Any Input					5	7.5		pF		

* T_{Low} = -55°C for HCC device - 40°C for HCF device

* T_{High} = +125°C for HCC device + 85°C for HCF device

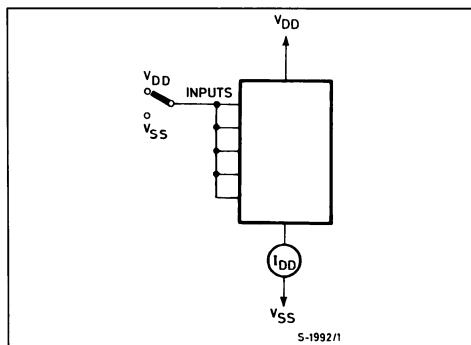
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

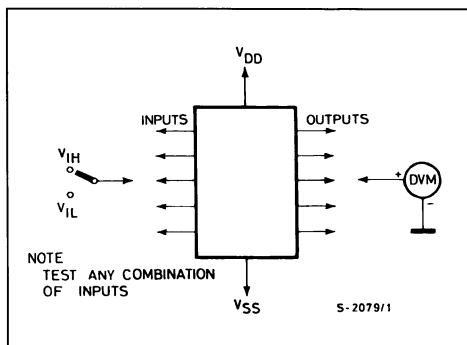
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			15		45	90	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

TEST CIRCUITS

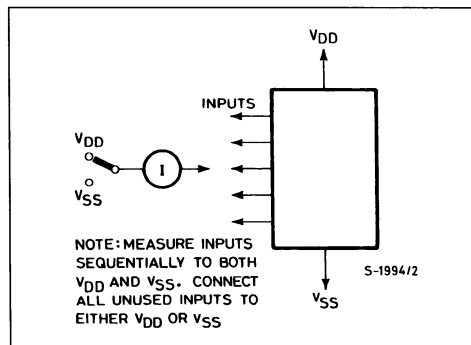
Quiescent Device Current.



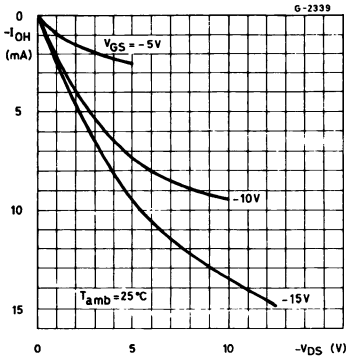
Noise Immunity.



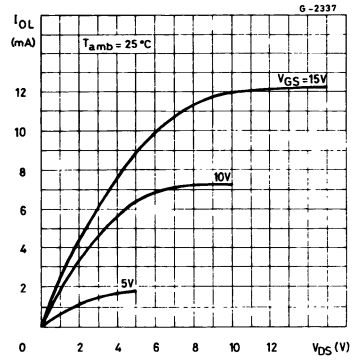
Input Leakage Current.



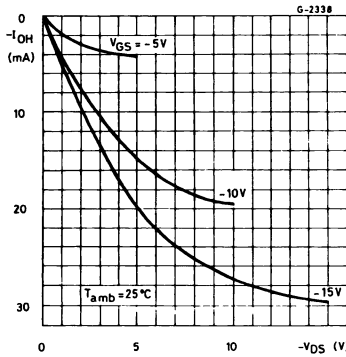
Minimum Output High (source) Current Characteristics.



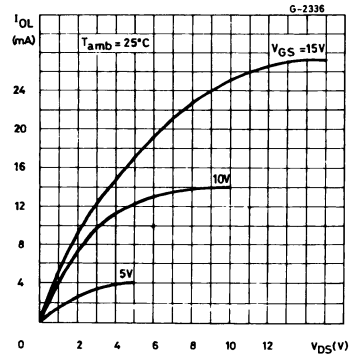
Minimum Output Low (sink) Current Characteristics.



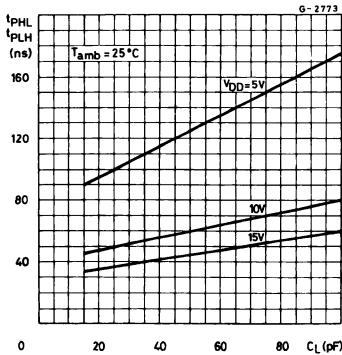
Typical Output High (source) Current Characteristics.



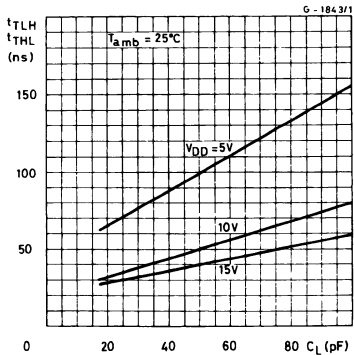
Typical Output Low (sink) Current Characteristics.



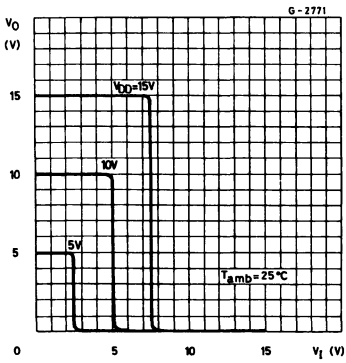
Typical Propagation Delay Time per Gate as a Function of Load Capacitance.



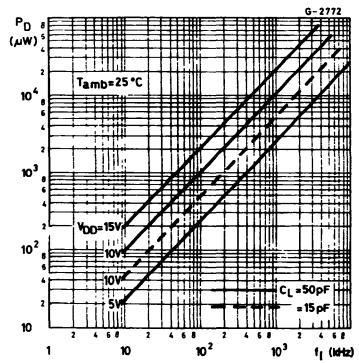
Typical Transition Time vs. Load Capacitance.



Typical Voltage Transfer Characteristics.

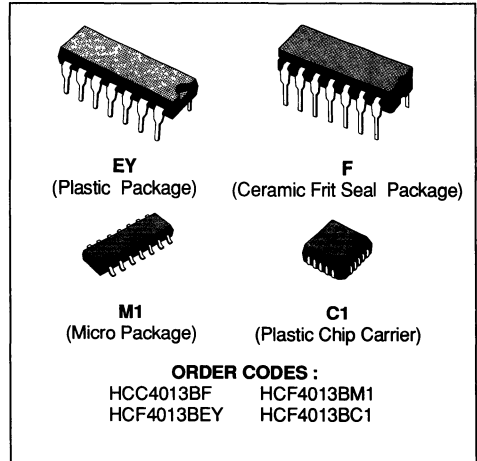


Typical Power Dissipation/gate vs Frequency.



DUAL 'D' - TYPE FLIP-FLOP

- SET-RESET CAPABILITY
- STATIC FLIP-FLOP OPERATION - RETAINS STATE INDEFINITELY WITH CLOCK LEVEL EITHER "HIGH" OR "LOW"
- MEDIUM-SPEED OPERATION - 16MHz (typ.) CLOCK TOGGLE RATE AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

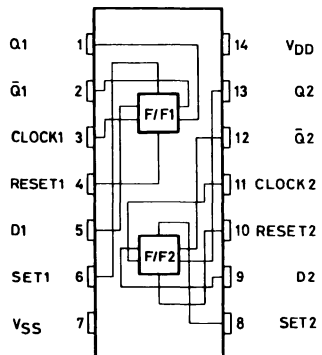


DESCRIPTION

The **HCC4013B** (extended temperature range) and **HCF4013B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4013B** consists of two identical, independent data-type flip-flops. Each flip-flop has independent data, set, reset, and clock inputs and Q and \bar{Q} outputs. These devices can be used for shift register applications, and, by connecting \bar{Q} output to the data input, for counter and toggle applications. The logic level present at the D input is transferred to the Q output during the positive-going transition of the clock pulse. Setting or resetting is independent of the clock and is accomplished by a high level on the set or reset line, respectively.

PIN CONNECTIONS



S-0550/1

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM AND TRUTH TABLE (one of two identical flip-flops)

*ALL INPUTS ARE PROTECTED BY
 COS/MOS PROTECTION NETWORK

PIN 14 = V_{DD}
 PIN 7 = V_{SS}

5-3223

CL ^A	D	R	S	Q	Q̄
	0	0	0	0	1
	1	0	0	1	0
	X	0	0	Q	Q̄
X	X	1	0	0	1
X	X	0	1	1	0
X	X	1	1	1	1

LOGIC 0 = LOW
 LOGIC 1 = HIGH

Δ = LOW LEVEL
 X = DON'T CARE
 N(N) = FF1/FF2 TERMINAL
 ASSIGNMENT

NO CHANGE

5 - 2299

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _{OH}	Output High Voltage			< 1	5	4.95		4.95			4.95		V	
				< 1	10	9.95		9.95			9.95			
				< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage		5/0	< 1	5		0.05			0.05		0.05	V	
			10/0	< 1	10		0.05			0.05		0.05		
			15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low}= - 55°C for HCC device : - 40°C for HCF device.

* T_{High}= + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

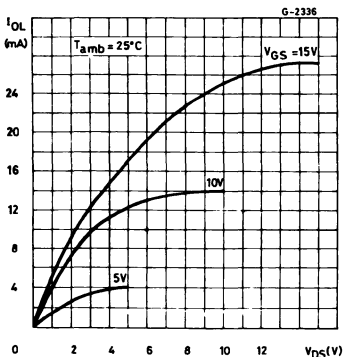
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time (clock to Q or Q outputs)		5		150	300	ns
			10		65	130	
			15		45	90	
t_{PLH}	Propagation Delay Time (set to Q or reset to Q)		5		150	300	ns
			10		65	130	
			15		45	90	
t_{PHL}	Propagation Delay Time (set to Q or reset to Q)		5		200	400	ns
			10		85	170	
			15		60	120	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}^*	Maximum Clock Input Frequency		5	3.5	7		MHz
			10	8	16		
			15	12	24		
t_w	Clock Pulse Width		5	140	70		ns
			10	60	30		
			15	40	20		
t_r , t_f^{**}	Clock Input Rise or Fall Time		5			15	μs
			10			4	
			15			1	
t_w	Set or Reset Pulse Width		5	180	90		ns
			10	80	40		
			15	50	25		
t_{setup}	Data Setup Time		5	40	20		ns
			10	20	10		
			15	15	7		

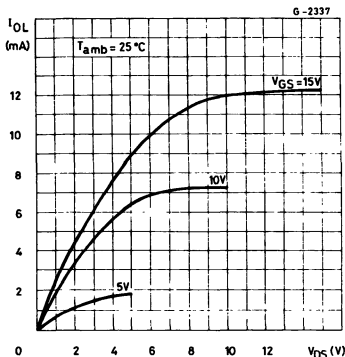
*Input t_r , $t_f = 5\text{ns}$.

** If more than unit is cascaded in a parallel clocked application, t_r should be made less than or equal to the sum of the fixed propagation delay time at 15pF and the transition time of the carry output driving stage for the estimated capacitive load.

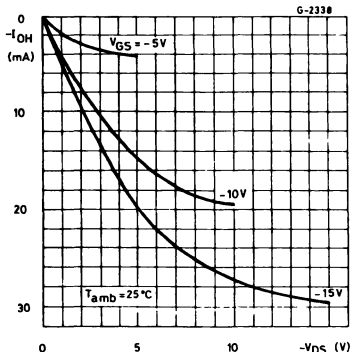
Typical Output Low (sink) Current Characteristics.



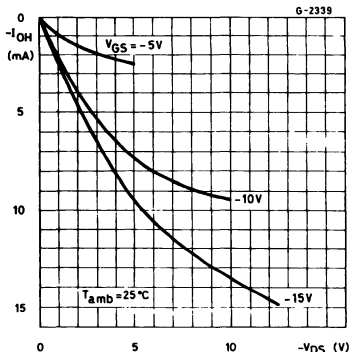
Minimum Output Low (sink) Current Characteristics.



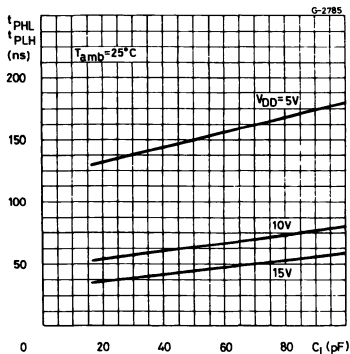
Typical Output High (source) Current Characteristics.



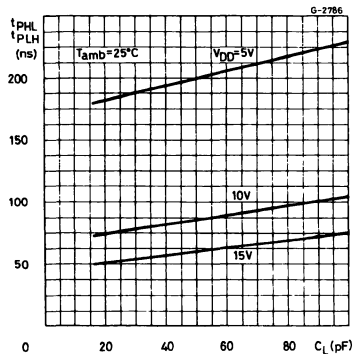
Minimum Output High (source) Current Characteristics.



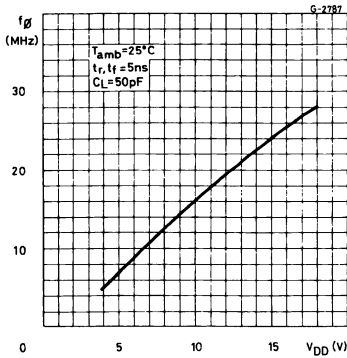
Typical Propagation Delay Time vs. Load Capacitance (CLOCK or SET to Q, CLOCK or RESET to \bar{Q}).



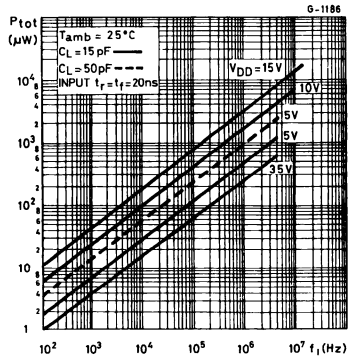
Typical Propagation Delay Time vs. Load Capacitance (SET to \bar{Q} or RESET to Q).



Typical Maximum Clock Frequency vs. Supply Voltage.

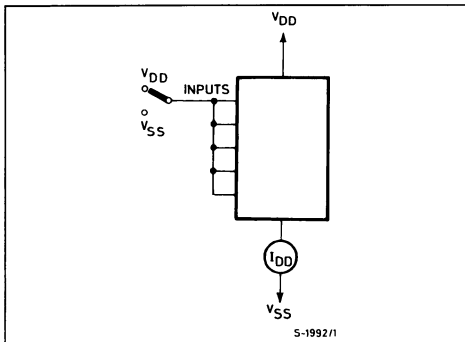


Typical Power Dissipation Device vs. Frequency.

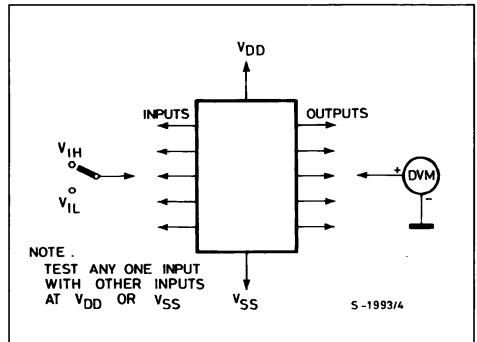


TEST CIRCUITS

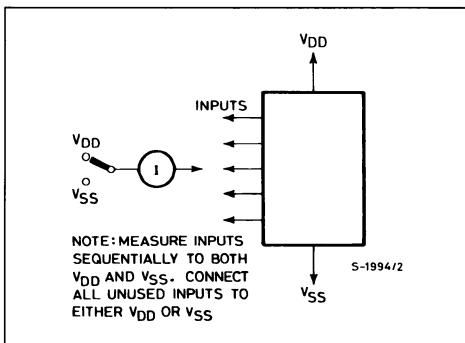
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.



8-STAGE STATIC SHIFT REGISTERS

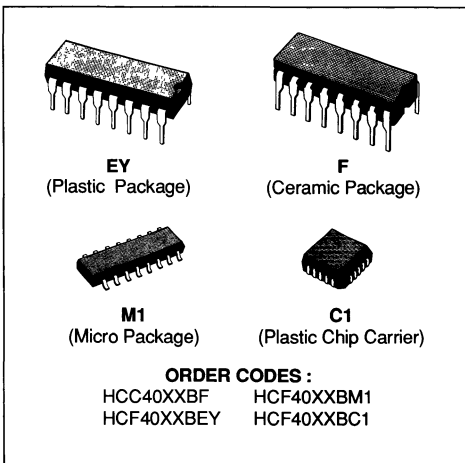
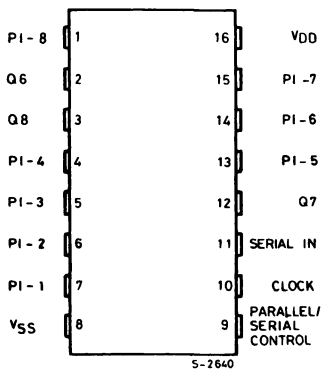
4014B SYNCHRONOUS PARALLEL OR SERIAL INPUT/SERIAL OUTPUT
4021B ASYNCHRONOUS PARALLEL INPUT OR SYNCHRONOUS SERIAL INPUT/SERIAL OUTPUT

- MEDIUM-SPEED OPERATION-12MHz (typ.)
CLOCK RATE AT $V_{DD} - V_{SS} = 10V$
- FULLY STATIC OPERATION
- 8 MASTER-SLAVE FLIP-FLOPS PLUS OUTPUT BUFFERING AND CONTROL GATING
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

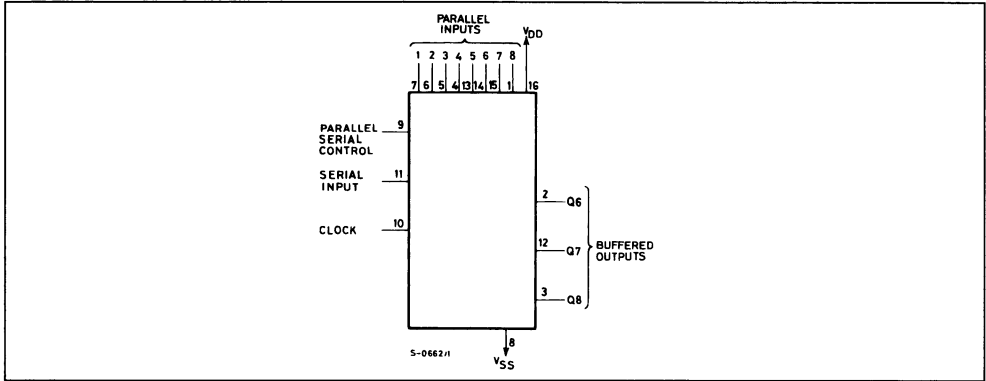
DESCRIPTION

The **HCC4014B**, **HCC4021B** (extended temperature range) and the **HCF4014B**, **HCF4021B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4014B** and **HCC/HCF4021B** series types are 8-stage parallel-or serial-input/serial-output registers having common CLOCK and PARALLEL/SERIAL CONTROL inputs, a single SERIAL data input, and individual parallel "JAM" inputs to each register stage. Each register stage is a D type, master-slave flip-flop in addition to an output from stage 8, "Q" outputs are also available from stages 6 and 7. Parallel as well as serial entry is made into the register synchronously with the positive clock line transition in the **HCC/HCF4014B**. In the **HCC/HCF4021B** serial entry is synchronous with the clock but parallel entry is asynchronous. In both types, entry is controlled by the PARALLEL/SERIAL CONTROL input. When the PARALLEL/SERIAL CONTROL input is low, data is serially shifted into the 8-stage register synchronously with the positive transition of the clock line. When the PARALLEL/SERIAL CONTROL input is high, data is jammed into the 8-stage

register via the parallel input lines and synchronous with the positive transition of the clock line. In the **HCC/HCF4021B**, the CLOCK input of the internal stage is "forced" when asynchronous parallel entry is made. Register expansion using multiple package is permitted.


PIN CONNECTIONS


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

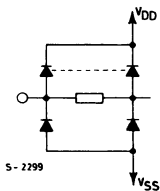
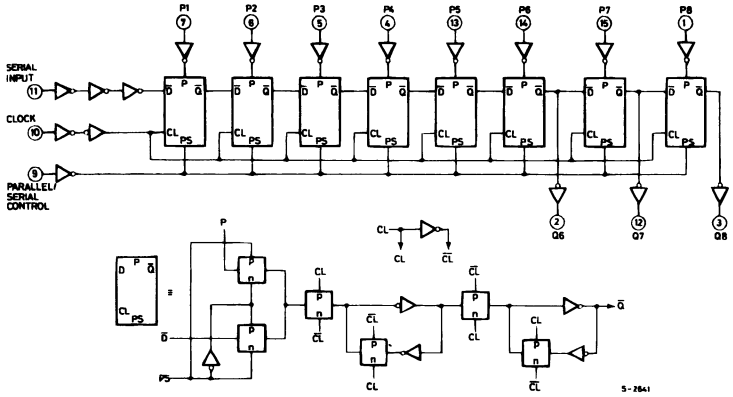
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$

LOGIC DIAGRAMS

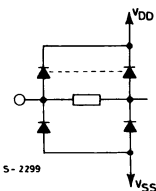
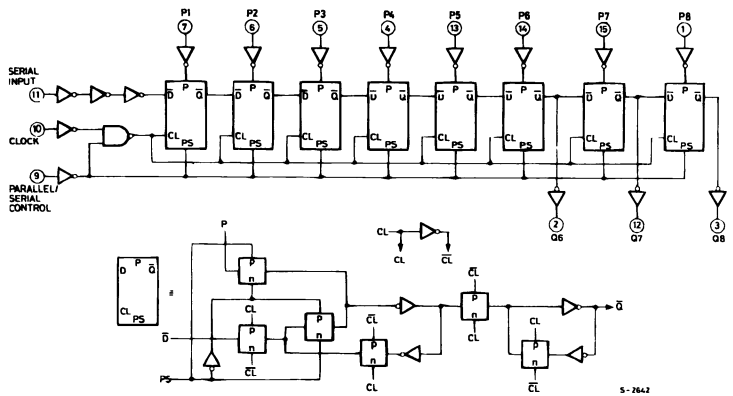
4014B



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

S-2841

4021B



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

S-2642

TRUTH TABLES

HCC/HCF 4014B

CL	Serial Input	Parallel/Serial Control	PI-1	PI-n	Q ₁ (internal)	Q _n
	X	1	0	0	0	0
	X	1	1	0	1	0
	X	1	0	1	0	1
	X	1	1	1	1	1
	0	0	X	X	0	Q _{n-1}
	1	0	X	X	1	Q _{n-1}
	X	X	X	X	Q ₁	Q _n

HCC/HCF4021B

CL	Serial Input	Parallel/Serial Control	PI-1	PI-n	Q ₁ (internal)	Q _n
X	X	1	0	0	0	0
X	X	1	0	1	0	1
X	X	1	1	0	1	0
X	X	1	1	1	1	1
	0	0	X	X	0	Q _{n-1}
	1	0	X	X	1	Q _{n-1}
	X	0	X	X	Q ₁	Q _n

X = don't care case.
NC = no change

X = don't care case.
NC = no change.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit			
		V _I (V)	V _O (V)	I _{Ol} (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *				
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.		
I _{CC}	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA	
			0/10			10		10		0.04	10		300		
			0/15			15		20		0.04	20		600		
			0/20			20		100		0.08	100		3000		
			HCF Types	0/ 5			5		20		0.04	20			150
				0/10			10		40		0.04	40			300
				0/15			15		80		0.04	80			600
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95			4.95			V		
		0/10	< 1	10	9.95		9.95			9.95					
		0/15	< 1	15	14.95		14.95			14.95					
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V		
		10/0	< 1	10		0.05			0.05		0.05				
		15/0	< 1	15		0.05			0.05		0.05				
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5				3.5		V		
		1/9	< 1	10	7		7				7				
		1.5/13.5	< 1	15	11		11				11				
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5			1.5		1.5		V		
		9/1	< 1	10		3			3		3				
		13.5/1.5	< 1	15		4			4		4				

* T_{Low} = - 55°C for HCC device - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit				
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *					
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15		mA		
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36				
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9				
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4				
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1				
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36				
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9				
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA		
			0/10	0.5		10	1.6		1.3	2.6		0.9				
			0/15	1.5		15	4.2		3.4	6.8		2.4				
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36				
			0/10	0.5		10	1.3		1.1	2.6		0.9				
			0/15	1.5		15	3.6		3.0	6.8		2.4				
		I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18	\pm 0.1		$\pm 10^{-5}$		\pm 0.1			\pm 1	μ A
				HCF Types	0/15		15	\pm 0.3		$\pm 10^{-5}$		\pm 0.3			\pm 1	
C _I	Input Capacitance		Any Input					5	7.5			pF				

* T_{Low} = - 55°C for HCC device . - 40°C for HCF device.* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin for both "1" and "0" level is . 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V.DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} = 0.3%/°C values, all input rise and fall time = 20ns)

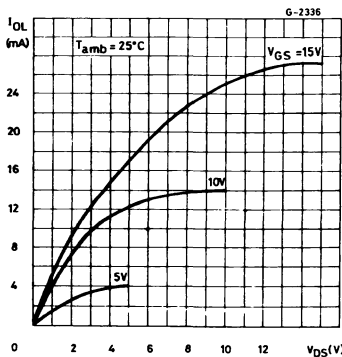
Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t _{PLH} , t _{PHL}	Propagation Delay Time		5		160	320	ns
			10		80	160	
			15		60	120	
t _{THL} , t _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f _{CL} *	Maximum Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8.5	17		
t _w	Clock Pulse Width		5	180	90		ns
			10	80	40		
			15	50	25		

* If more than one unit is cascaded t_{CL} should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage of the estimated capacitive load.

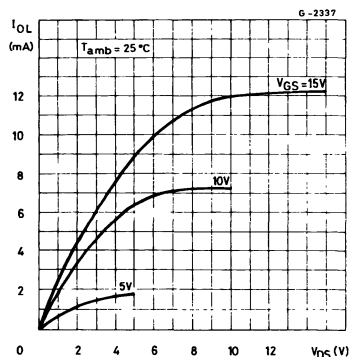
Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t _r , t _f	Clock Input Rise or Fall Time		5			15	μs
			10			15	
			15			15	
t _{setup}	Setup Time, serial Input (ref to CL)		5	120	60		ns
			10	80	40		
			15	60	30		
t _{setup}	Setup Time, parallel Inputs (4014B) (ref. to CL)		5	80	40		ns
			10	50	25		
			15	40	20		
t _{setup}	Setup Time, parallel Inputs (4021B) (ref. to P/S)		5	50	25		ns
			10	30	15		
			15	20	10		
t _{setup}	Setup Time, parallel/serial Control (4014B) (ref. to CL)		5	180	90		ns
			10	80	40		
			15	60	30		
t _{hold}	Hold Time, serial in, parallel in, parallel/serial Control		5	0			ns
			10	0			
			15	0			
t _{WH}	P/S Pulse Widht (4021B)		5	160	80		ns
			10	80	40		
			15	50	25		
t _{rem}	P/S Removal, time (4021B) (ref. to CL)		5	280	140		ns
			10	140	70		
			15	100	50		

* If more than one unit is cascaded t_{CL} should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage of the estimated capacitive load.

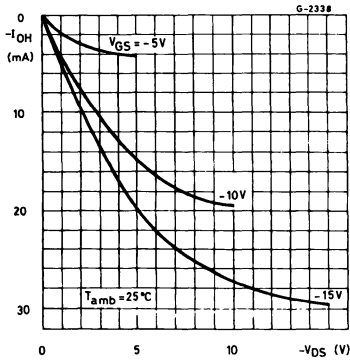
Typical Output Low (sink) Current Characteristics.



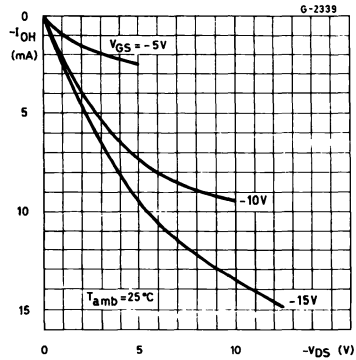
Minimum Output Low (sink) Current Characteristics.



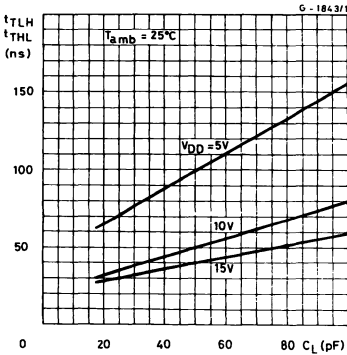
Typical Output High (source) Current Characteristics.



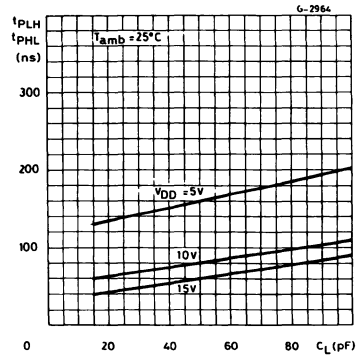
Minimum Output High (source) Current Characteristics.



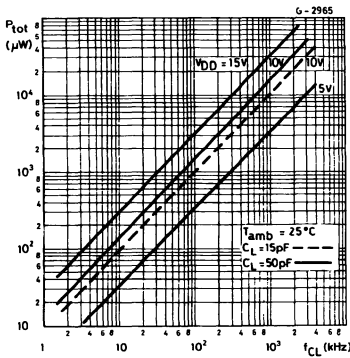
Typical Transition Time vs. Load Capacitance.



Typical Propagation Delay Time vs. Load Capacitance.

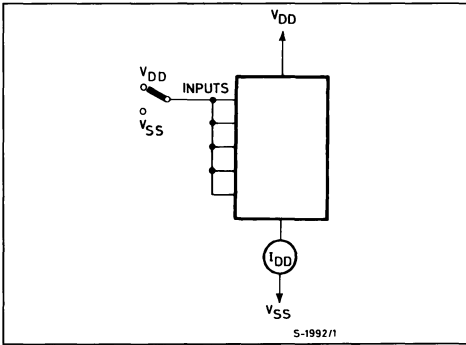


Typical Dynamic Power Dissapating vs. Clock Input Frequency.

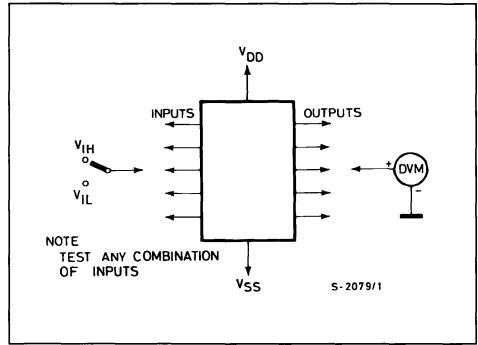


TEST CIRCUITS

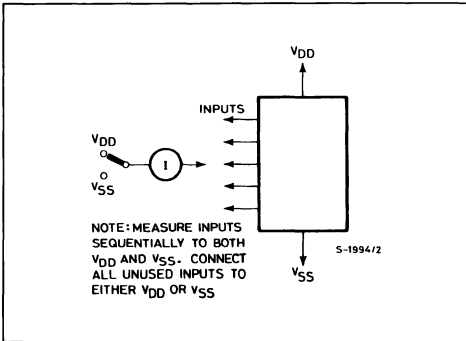
Quiescent Device Current.



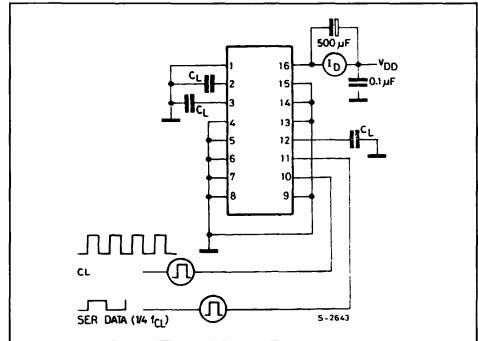
Noise Immunity.



Input Leakage Current.

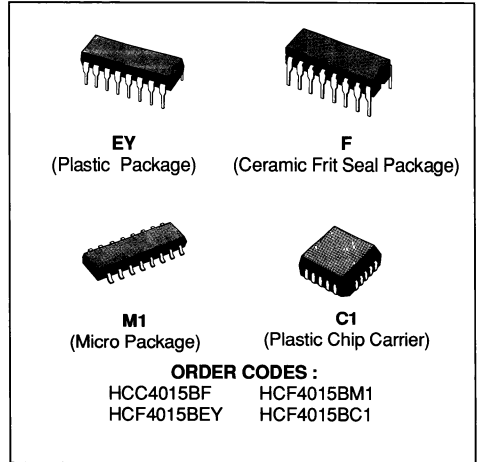


Dynamic Power Dissipation.



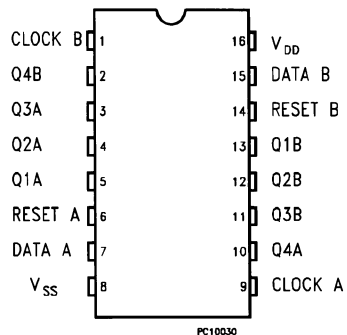
DUAL 4-STAGE STATIC SHIFT REGISTER WITH SERIAL INPUT/PARALLEL OUTPUT

- MEDIUM SPEED OPERATION : 12MHz (typ.)
CLOCK RATE AT $V_{DD} - V_{SS} = 10V$
- FULLY STATIC OPERATION
- 8 MASTER-SLAVE FLIP-FLOPS PLUS INPUT AND OUTPUT BUFFERING
- HIGH NOISE IMMUNITY
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

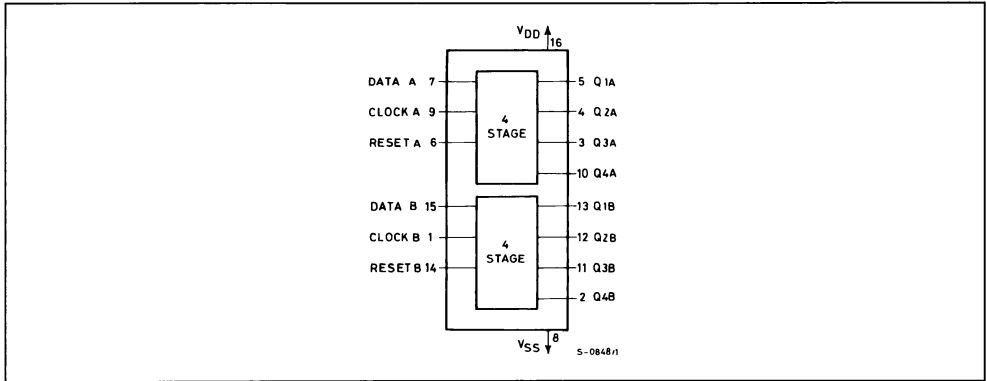

DESCRIPTION

The **HCC4015B** (extended temperature range) and **HCF4015B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4015B** consists of two identical, independent, 4-stage serial-input/parallel-output registers. Each register has independent **CLOCK** and **RESET** inputs as well as a single serial **DATA** input. "Q" outputs are available from each of the four stages on both registers. All register stages are D-type, master-slave flip-flops. The logic level present at the **DATA** input is transferred into the first register stage and shifted over one stage at each positive-going clock transition. Resetting of all stages is accomplished by a high level on the reset line. Register expansion to 8 stages using one **HCC/HCF4015B** package, or to more than 8 stages using additional **HCC/HCF4015B**'s is possible.

PIN CONNECTIONS


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

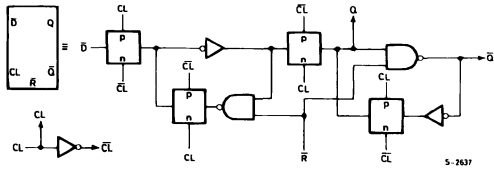
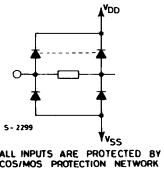
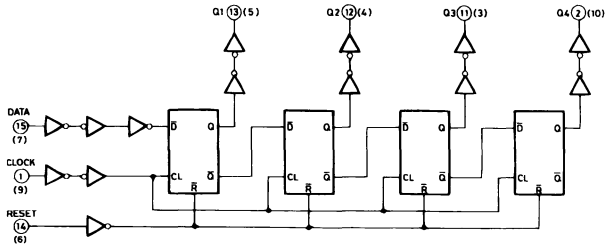
Stresses above those listed under "Absolute Maximum Ratings "may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS AND TRUTH TABLE



CL	D	R	Q ₁	Q _n
┌	0	0	0	Q _{n-1}
┐	1	0	1	Q _{n-1}
└	X	0	Q ₁	Q _{n-1} (no. change)
X	X	1	0	0

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low}= - 55°C for HCC device : - 40°C for HCF device

* T_{High}= + 125°C for HCC device : + 85°C for HCF device

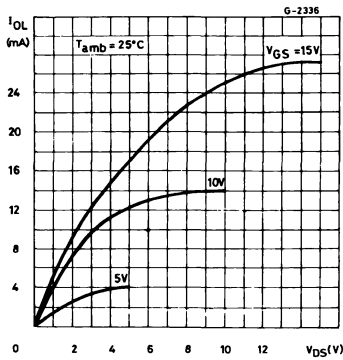
The Noise Margin for both "1" and "0" levels is . 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ }^{\circ}\text{C}/\%$, all input rise and fall times = 20 ns)

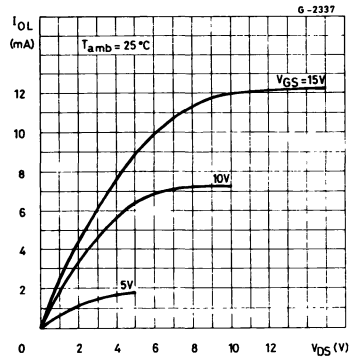
Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
CLOCKED OPERATION							
t_{PLH}, t_{PHL}	Propagation Delay Time (carry out or decoded out lines)		5		160	320	ns
			10		80	160	
			15		60	120	
t_{THL}, t_{TLH}	Transition Time (carry out or decoded out lines)		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}	Maximum Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8.5	17		
t_w	Clock Pulse Width		5	180	90		ns
			10	80	40		
			15	50	25		
t_r, t_f^*	Clock Input Rise or Fall Time		5			15	μs
			10			15	
			15			15	
t_{setup}	Data Setup Time		5	70	35		ns
			10	40	20		
			15	30	15		
RESET OPERATION							
t_{PLH}, t_{PHL}	Propagation Delay Time		5		200	400	ns
			10		100	200	
			15		80	160	
t_w	Reset Pulse Width		5	200	100		ns
			10	80	40		
			15	60	30		

* If more than unit is cascaded in the parallel clocked application, t_{CL} should be made less than or equal to the sum of the fixed propagation delay at 15 pF and the transition time of the carry output driving stage for the estimated capacitive load

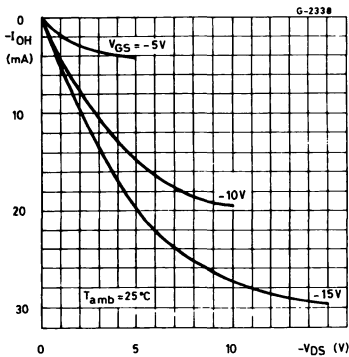
Typical Output Low (sink) Current Characteristics.



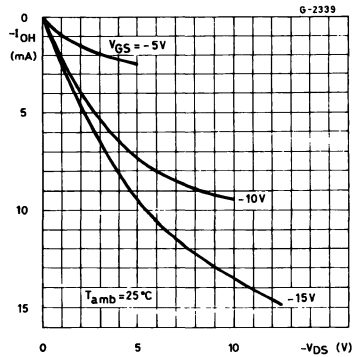
Minimum Output Low (sink) Current Characteristics.



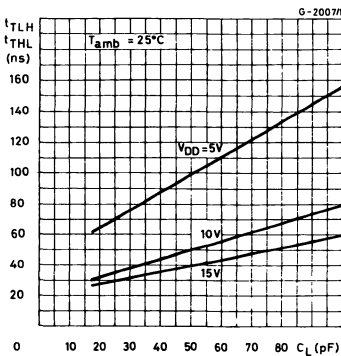
Typical Output High (source) Current Characteristics.



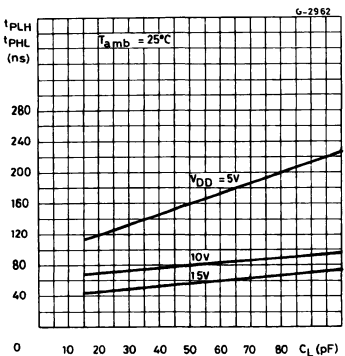
Minimum Output High (source) Current Characteristics.



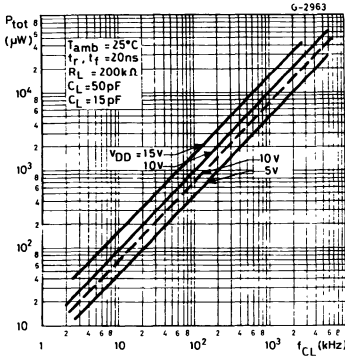
Typical transition Time vs. Load Capacitance.



Typical propagation Delay Time vs. Load Capacitance..

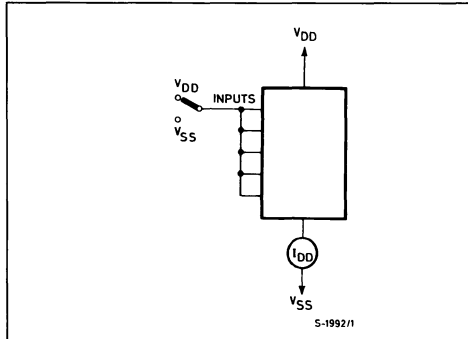


Typical Dynamic Power Dissipation vs. Frequency.

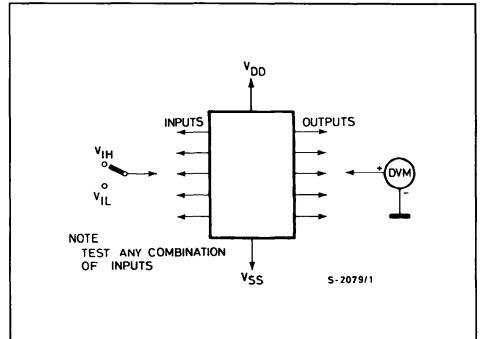


TEST CIRCUITS

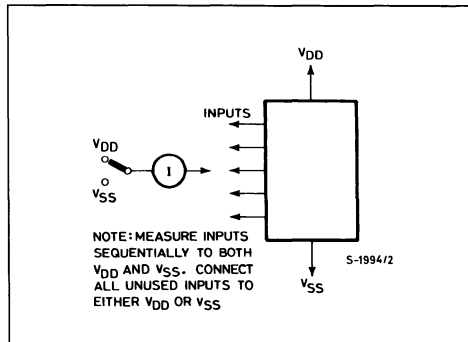
Quiescent Device Current.



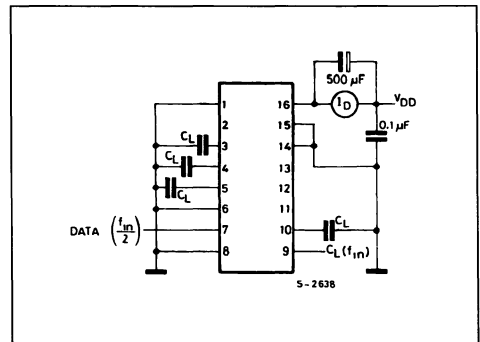
Input current.



Input Voltage.



Power Dissipation.



QUAD BILATERAL SWITCH

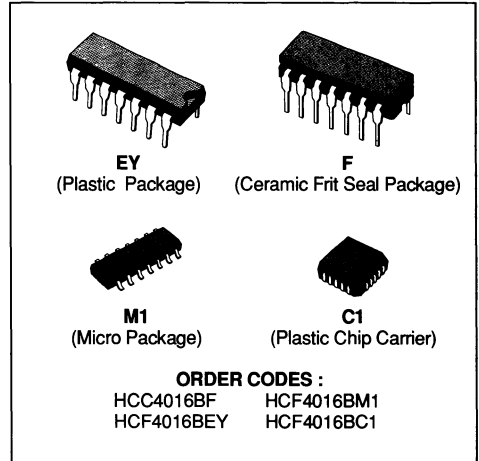
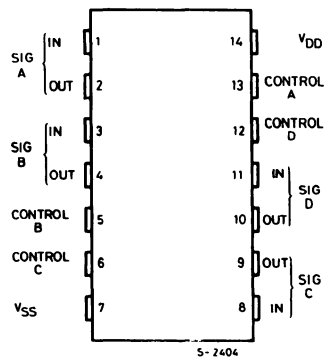
- 20V DIGITAL OR $\pm 10V$ PEAK-TO-PEAK SWITCHING
- 280 Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- SWITCH ON RESISTANCE MATCHED TO WITHIN 10 Ω TYP. OVER 15V SIGNAL INPUT RANGE
- HIGH ON/OFF OUTPUT-VOLTAGE RATIO : 65dB TYP. @ $f_{is} = 10kHz$, $R_L = 10k\Omega$
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. @ $f_{is} = 1kHz$, $V_{is} = 5 V_{pp}$, $V_{DD} - V_{SS} \geq 10V$, $R_L = 10k\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE: 100pA TYP. @ $V_{DD} - V_{SS} = 18V$, $T_{amb} = 25^\circ C$
- EXTREMELY HIGH CONTROL INPUT IMPEDANCE (control circuit isolated from signal circuit 10¹² Ω typ.)
- LOW CROSSTALK BETWEEN SWITCHES : 50dB TYP. @ $f_{is} = 0.9MHz$, $R_L = 1k\Omega$
- MATCHED CONTROL-INPUT TO SIGNAL-OUTPUT CAPACITANCE : REDUCES OUTPUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE' SWITCH ON = 40MHz (typ.)
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25 $^\circ C$ FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N' 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

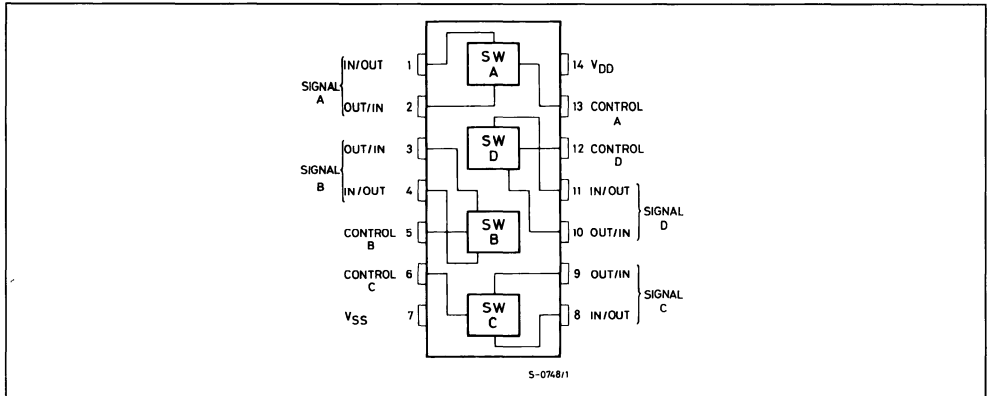
The **HCC4016B** (extended temperature range) and **HCF4016B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4016B** Series types are quad bilateral switches intended for the transmission or multiplexing

of analog or digital signals. Each of the four independent bilateral switches has a single control signal input which simultaneously biases both the p and n device in a given switch ON or OFF.


PIN CONNECTIONS


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

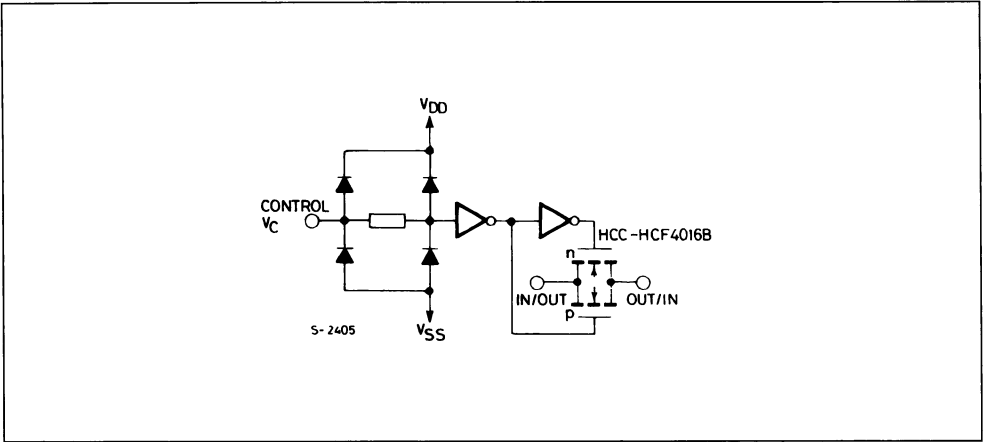
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

SCHEMATIC DIAGRAM

1 OF 4 IDENTICAL SECTION



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions			Value						Unit	
			V _C = V _{DD}	V _{SS} (V)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Device Current (all switches on or all switches off)	HCC Types	V _{DD}	V _{SS}	5	0.25	0.01	0.25		7.5	μA		
					10	0.5	0.01	0.5	15				
					15	1	0.01	1	30				
					20	5	0.02	5	150				
		HCF Types			5	1	0.01	1	7.5				
					10	2	0.01	2	15				
		15	4	0.01	4	30							
SWITCH					V _{IS}								
R _{ON}	Resistance	HCC	R _L = 10kΩ	+ 7.5	- 7.5	+ 7.5	360		200	400		600	Ω
						- 7.5	360		200	400		600	
						± 0.25	775		280	850		1230	
		HCF				+ 7.5	370		200	400		520	
						- 7.5	370		200	400		520	
						± 0.25	790		280	850		1080	
HCC	R _L = 10kΩ	+ 5	- 5	+ 5	600		250	660		960			
				- 5	600		250	660		960			
				± 0.25	1870		580	2000		2600			
HCF				+ 5	610		250	660		840			
				- 5	610		250	660		840			
				± 0.25	1900		580	2000		2380			

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device
 * T_{High} = + 125°C for HCC device ; + 85°C for HCF device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions					Value						Unit	
			V _C = V _{SS} V _{DD} (V)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *				
					Min.	Max.	Min.	Typ.	Max.	Min.	Max.			
SWITCH (continued)														
R _{ON}	Resistance	HCC	R _L = 10kΩ	+ 15	0	+ 15 + 0.25 + 9.3	360 360 775		200 200 300	400 400 850		600 600 1230	Ω	
				HCF	+ 15	0	+ 15 + 0.25 + 9.3	370 370 790		200 200 300	400 400 800			520 520 1080
		HCC	R _L = 10kΩ		+ 10	0	+ 10 + 0.25 + 5.6	600 600 1870		250 250 560	660 660 2000			960 960 2600
				HCF	+ 10	0	+ 10 + 0.25 + 5.6	610 610 1900		250 250 560	660 660 2000			840 840 2380
ΔON	Resistance ΔRON (between any 2 of 4 switches)	R _L = 10kΩ	+ 7.5		- 7.5	± 7.5			10				Ω	
			+ 5	- 5	± 5			15						
Input or Output Leakage Current Switch OFF (effective off resistance)		HCC	V _{DD}	V _C = V _{SS} 0			± 0.1		10 ⁻⁵	± 0.1		1	μA	
		HCF	V _{DD}	V _C = V _{SS} 0			± 0.3		10 ⁻⁵	± 0.3		1		
C _I	Input Capacitance	V _{CC} = V _{SS} = - 5			+ 5			4				pF		
C _O	Output Capacitance							4						
C _{IO}	Feedthrough							0.2						
CONTROL (V_C)														
V _{TH}	Switch Threshold Voltage	I _{IS} = 10μA			5	1		1	2.25		1		V	
					10	2		2	4.5		2			
					15	2		2	6.75		2			
I _I	Input Current	HCC Types	V _{IS} ≤ V _{DD}			18		± 0.1		± 10 ⁻⁵	± 0.1		± 1	μA
		HCF Types				15		± 0.3		± 10 ⁻⁵	± 0.3		± 1	
C _I	Input Capacitance							5	7.5			pF		

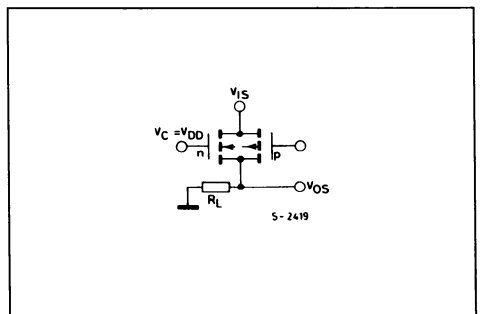
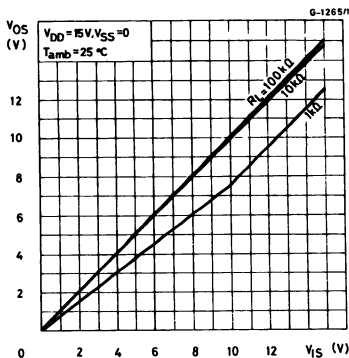
* T_{Low} = - 55°C for HCC device - 40°C for HCF device.
 * T_{High} = + 125°C for HCC device . + 85°C for HCF device.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$ all input square wave rise and fall time = 20ns)

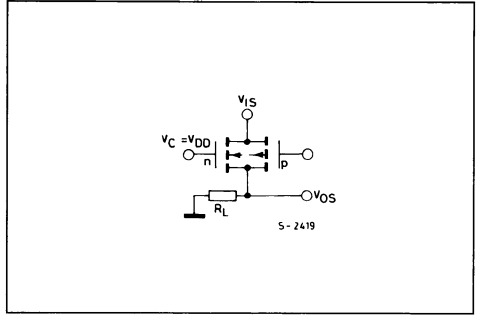
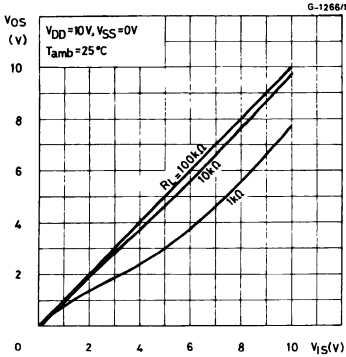
Parameter	Test Conditions						Value		Unit	
	V_C (V)	R_L (k Ω)	f_i (KHz)	V_I (V)	V_{SS} (V)	V_{DD} (V)	Typ.	Max.		
SWITCH										
t_{pd} Propagation Delay Time (signal input to output)	$= V_{DD}$	10		10sq. Wave	GND	5 10 15	40 20 15	100 50 40	ns	
Crosstalk Between any 2 of 4 Switches ($f @ -50\text{dB}$) $20 \log 10 \frac{V_{O(B)}}{V_{I(A)}} = -50\text{dB}$	$V_{C(A)} = V_{DD} = +5$ $V_{C(B)} = V_{SS} = -5$	1		$V_{I(A)} \Delta = 5\text{p-p}$			0.9		MHz	
Frequency Response Switch "ON" (sine wave input) At $20 \log 10 \frac{V_O}{V_I} = -3\text{dB}$	$= V_{DD} = +5$	1		5p-p	-5		40		MHz	
Feedthrough (switch OFF) At $20 \log 10 \frac{V_O}{V_I} = -50\text{dB}$	$= V_{SS} = -5$	1		-5p-p		5	1.25		MHz	
Sine Wave Distortion	$= V_{DD} = 5$	10	1	5p-p	-5		0.4		%	
CONTROL (V_C)										
Propagation Delay : (turn on control to output)	$V_{DD} - V_{SS}$ (sq. wave)	1		V_{DD} or V_{SS}		5 10 15	$V_{DD}-V_{SS} = 10\text{V}$	35 20 15	70 40 30	ns
Max. Allowable Control Input Repetition Rate	10 (sq. wave)	1		V_{DD}	GND	10		10		MHz
Crosstalk (control input to signal output)	10 (sq. wave)	10			GND	10		50		mV

(A) Symmetrical about OV

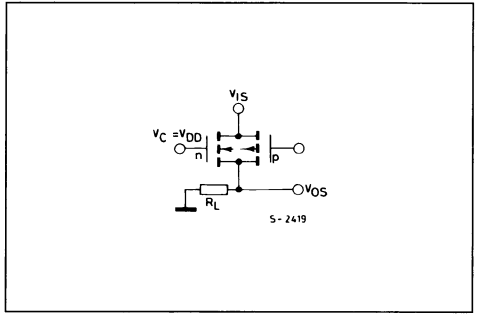
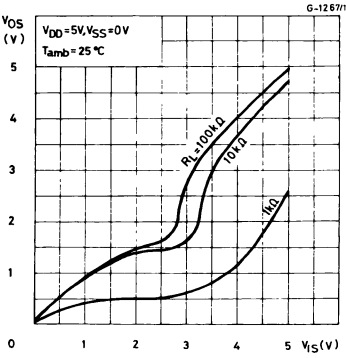
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +15\text{V}$, $V_{SS} = 0\text{V}$, and Test Circuit.



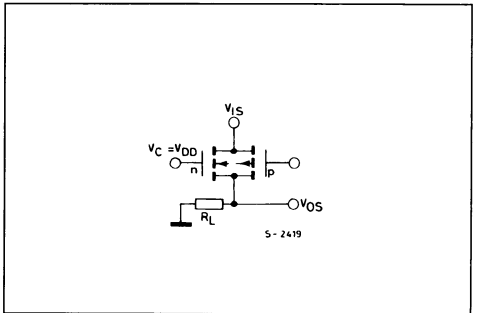
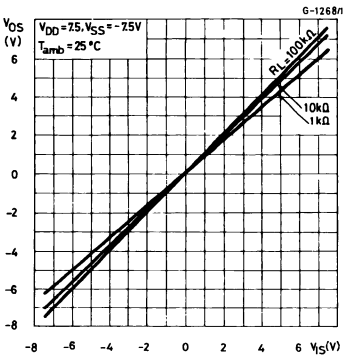
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +10V$, $V_{SS} = 0V$, and Test Circuit.



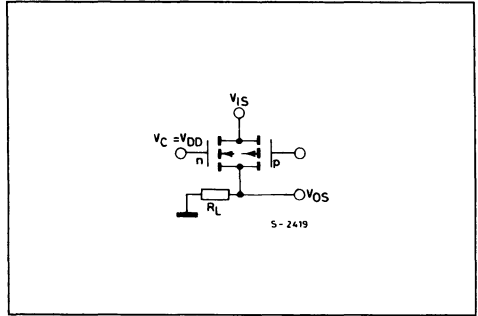
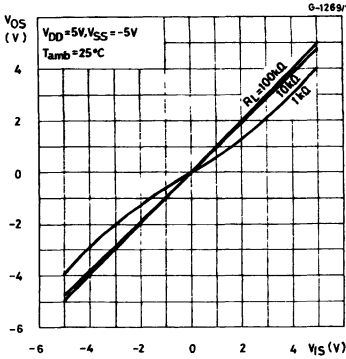
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +5V$, $V_{SS} = 0V$, and Test Circuit.



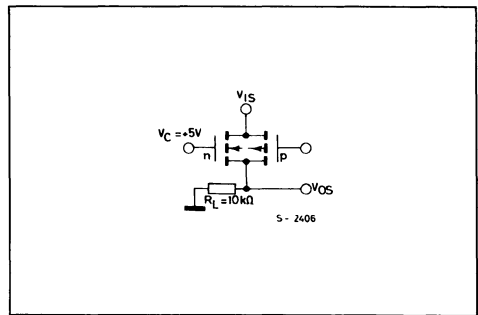
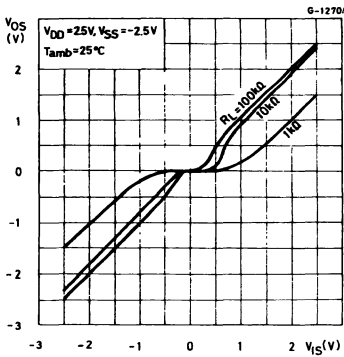
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +7.5V$, $V_{SS} = -7.5V$, and Test Circuit.



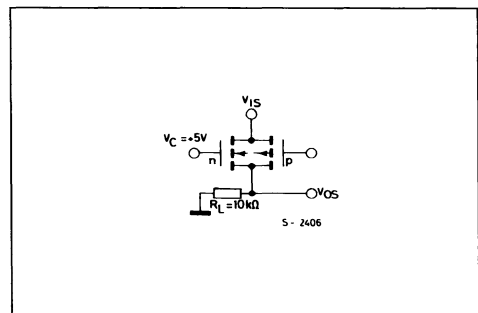
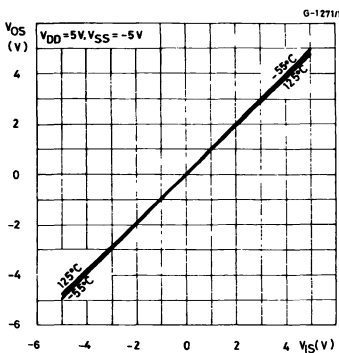
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +5V$, $V_{SS} = -5V$, and Test Circuit.



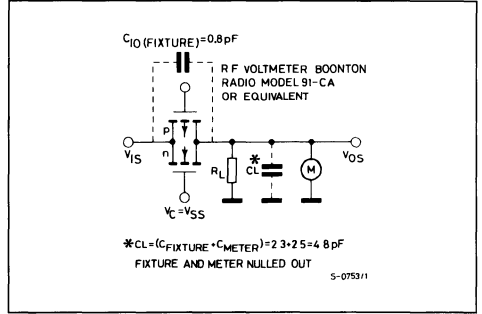
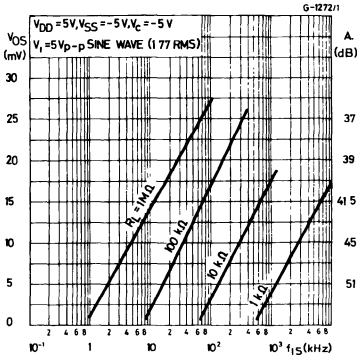
Typical "ON" Characteristics for 1 of 4 switches with $V_{DD} = +2.5V$, $V_{SS} = -2.5V$, and Test Circuit.



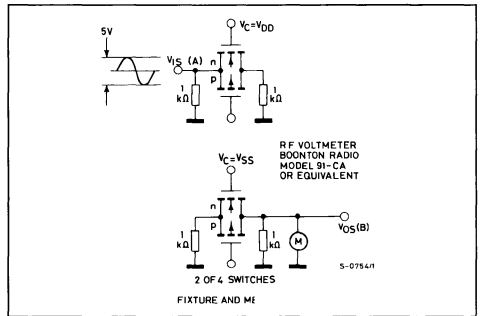
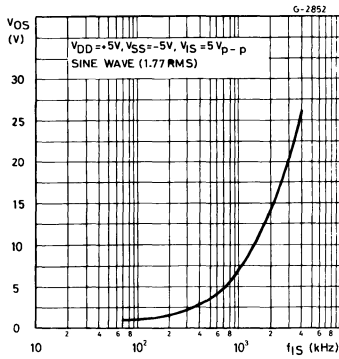
Typical "ON" Characteristics as function of temp. for 1 of 4 switches with $V_{DD} = +5V$ and Test Circuit.



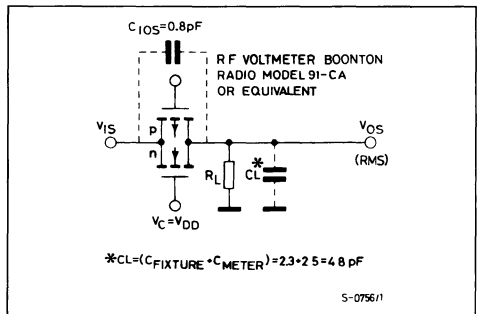
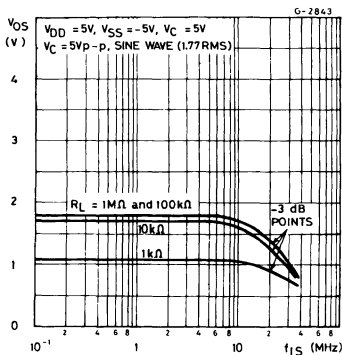
Typical feedthru vs. frequency-switch "OFF" and Test Circuit.



Typical Crosstalk between Switch Circuits in the Same Package.



Typical Switch Frequency response-switch "ON" and Test Circuit.



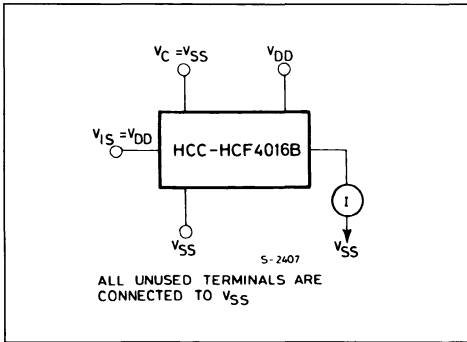
TYPICAL "ON" RESISTANCE CHARACTERISTICS, $T_{amb} = 25^{\circ}\text{C}$

Characteristic*	Supply Conditions		Load Conditions					
			$R_L = 1\text{ k}\Omega$		$R_L = 10\text{ k}\Omega$		$R_L = 100\text{ k}\Omega$	
	V_{DD} (V)	V_{SS} (V)	Value (Ω)	V_{is} (V)	Value (Ω)	V_{is} (V)	Value (Ω)	V_{is} (V)
R_{ON}	+ 15	0	200	+ 15	200	+ 15	180	+ 15
			200	0	200	0	200	0
$R_{ON} \text{ (max)}$	+ 15	0	300	+ 11	300	+ 9.3	320	+ 9.2
R_{ON}	+ 10	0	290	+ 10	250	+ 10	240	+ 10
			290	0	250	0	300	0
$R_{ON} \text{ (max)}$	+ 10	0	500	+ 7.4	560	+ 5.6	610	+5.5
R_{ON}	+ 5	0	860	+ 5	470	+ 5	450	+ 5
			600	0	580	0	800	0
$R_{ON} \text{ (max)}$	+ 5	0	1.7k	+ 4.2	7k	+ 2.9	33k	+2.7
R_{ON}	+ 2.5	- 2.5	590	+ 2.5	450	+ 2.5	490	+ 2.5
			720	- 2.5	520	- 2.5	520	- 2.5
$R_{ON} \text{ (max)}$	+ 2.5	- 2.5	232k	± 0.25	300k	± 0.25	870k	± 0.25

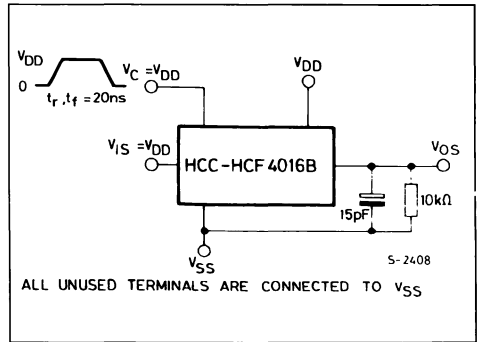
* Variation from a perfect switch, $R_{ON} = 0\Omega$.

TEST CIRCUITS

"OFF" Switch Input or Put Leakage Current.

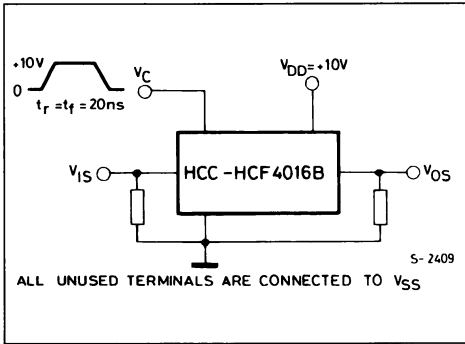


Square-Wave Response.

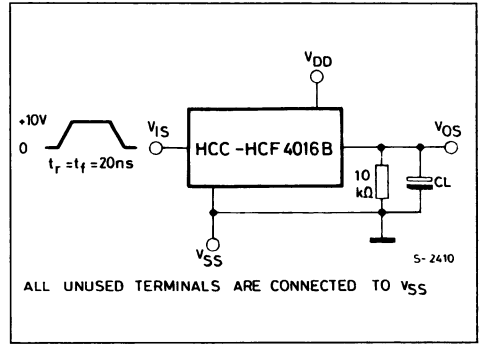


TEST CIRCUITS (continued)

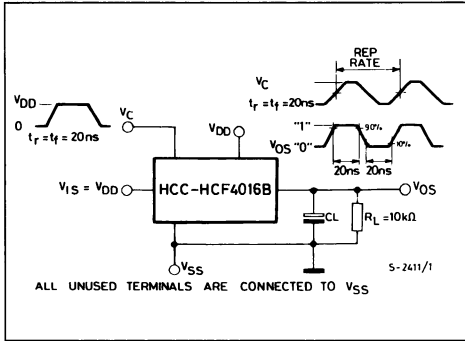
Crosstalk-control Input to Signal Output.



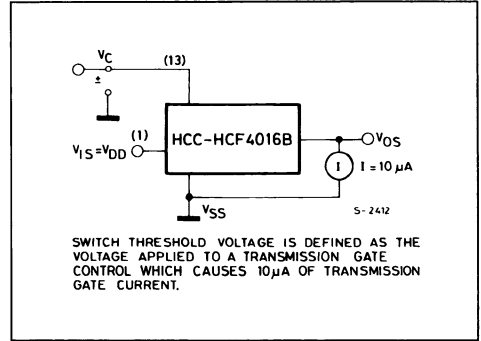
Propagaton Delay Time Signal Input (V_{IS}) to Signal Output (V_{OS}).



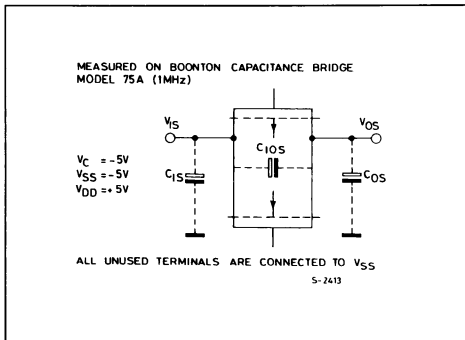
Max Allowable Control-input Repetition Rate.



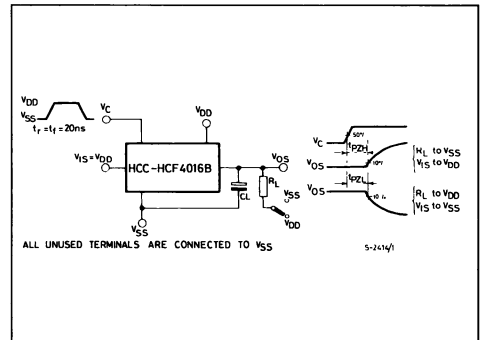
Switch Threshold Voltage.



Capacitance C_{IOS} and C_{OS}.

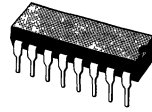
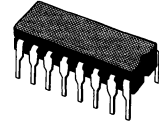
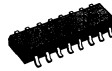


Turn-On Propagation Delay-control Input to Output.



COUNTERS/DIVIDERS
**4017B DECADE COUNTER WITH 10
 DECODED OUTPUTS**
**4022B OCTAL COUNTER WITH 8
 DECODED OUTPUTS**

- FULLY STATIC OPERATION
- MEDIUM SPEED OPERATION-12MHz (typ.) AT $V_{DD} = 10V$
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


EY
 (Plastic Package)

F
 (Ceramic Frit Seal Package)

M1
 (Micro Package)

C1
 (Plastic Chip Carrier)

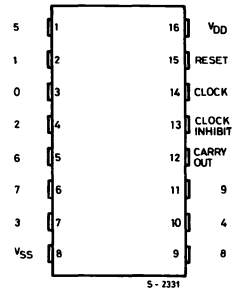
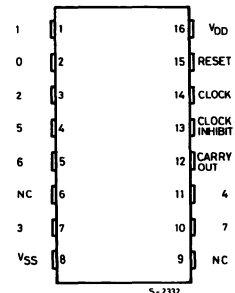
ORDER CODES :

HCC40XXBF	HCF40XXBM1
HCF40XXBEY	HCF40XXBC1

DESCRIPTION

The **HCC4017B/4022B** (extended temperature range) and **HCF4017B/4022B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

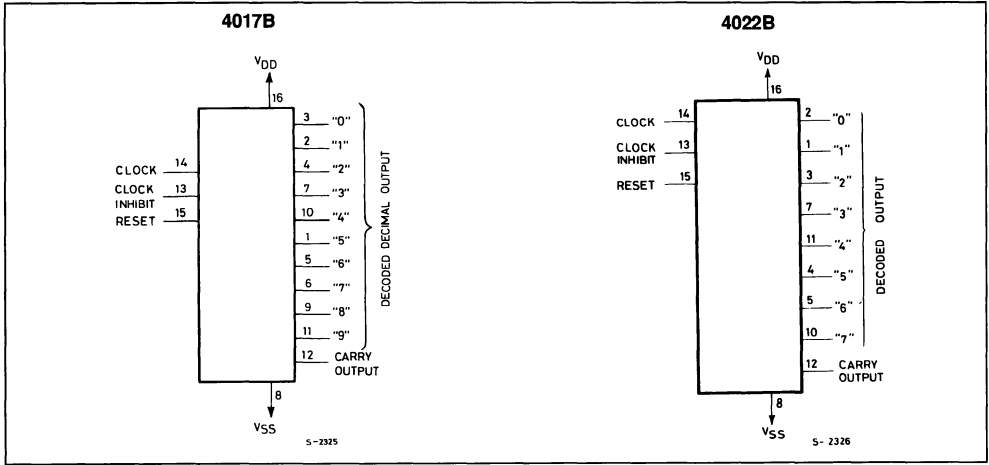
The **HCC/HCF4017B** and **HCC/HCF4022B** are 5-stage and 4-stage Johnson counters having 10 and 8 decoded outputs, respectively. Inputs include a **CLOCK**, a **RESET**, and a **CLOCK INHIBIT** signal. Schmitt trigger action in the **CLOCK** input circuit provides pulse shaping that allows unlimited clock input pulse rise and fall times. These counters are advanced one count at the positive clock signal transition if the **CLOCK INHIBIT** signal is low. Counter advancement via the clock line is inhibited when the **CLOCK INHIBIT** signal is high. A high **RESET** signal clears the counter to its zero count. Use of the Johnson decade-counter configuration permits high-speed operation, 2-input decimal-decode gating, and spike-free decoded outputs. Anti-lock gating is provided, thus assuring proper counting sequence. The decoded outputs are normally low and go high only at their respective decoded time slot. Each decoded output remains high for one full clock cycle. A **CARRY-OUT** signal completes one cycle every

PIN CONNECTIONS
4017B

4022B


10 clock input cycles in the **HCC/HCF4017B** or every 8 clock input cycles in the **HCC/HCF4022B** and

is used to ripple-clock the succeeding device in a multi-device counting chain.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

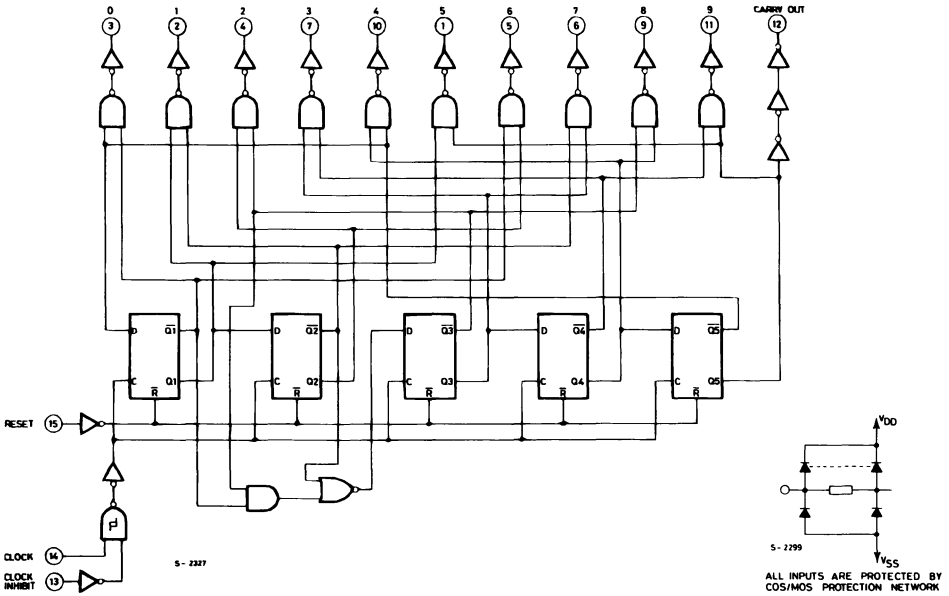
* All voltages values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

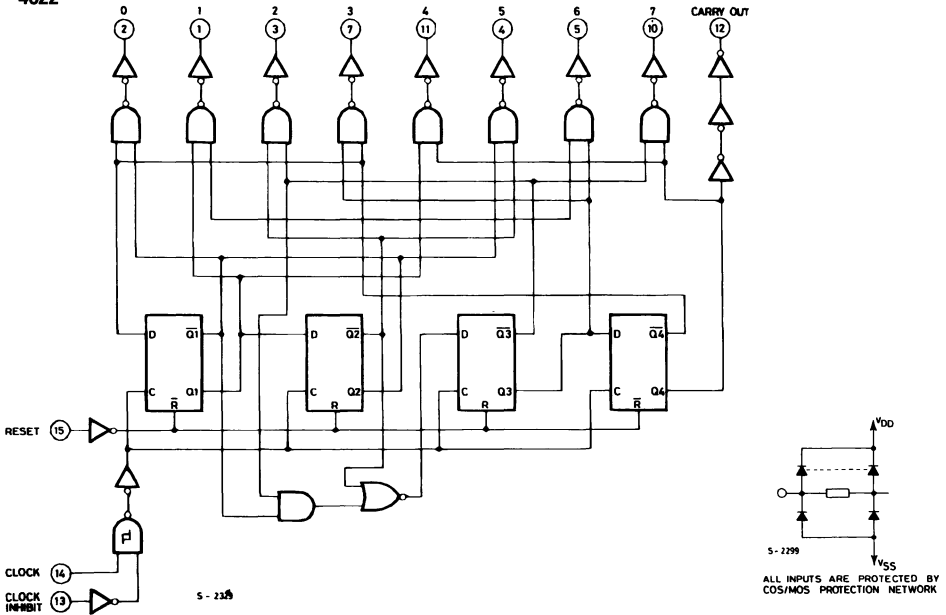
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS

4017B

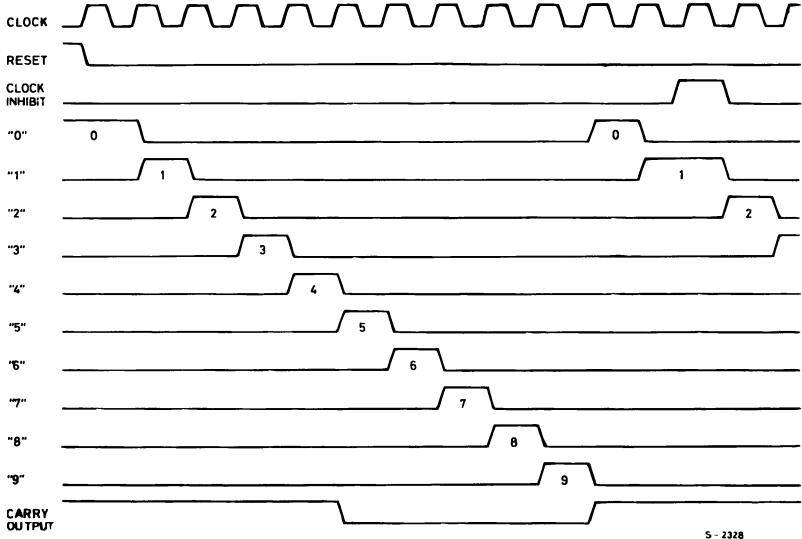


4022

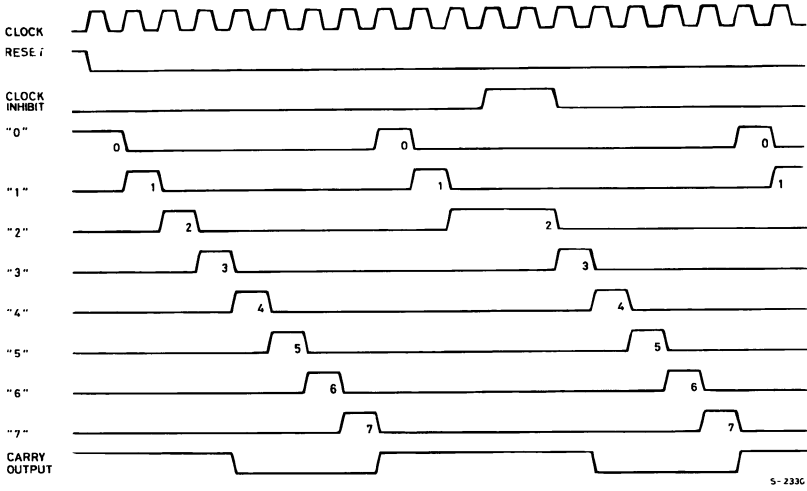


TIMING DIAGRAMS

4017B



4022B



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit			
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *				
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.		
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A		
			0/10			10		10		0.04	10		300			
			0/15			15		20		0.04	20		600			
			0/20			20		100		0.08	100		3000			
		HCF Types	0/ 5			5		20		0.04	20		150			
			0/10			10		40		0.04	40		300			
			0/15			15		80		0.04	80		600			
V _{OH}	Output High Voltage		0/ 5		< 1	5	4.95		4.95			4.95		V		
			0/10		< 1	10	9.95		9.95			9.95				
			0/15		< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage		5/0		< 1	5		0.05			0.05		0.05	V		
			10/0		< 1	10		0.05			0.05		0.05			
			15/0		< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage			0.5/4.5	< 1	5	3.5		3.5			3.5		V		
				1/9	< 1	10	7		7			7				
				1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage			4.5/0.5	< 1	5		1.5			1.5		1.5	V		
				9/1	< 1	10		3			3		3			
				13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		-	1.15	mA		
			0/ 5	4.6		5	-	0.64		-	- 1		-		0.36	
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		-	- 0.9			
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		-	- 2.4			
		HCF Types	0/ 5	2.5		5	-		1.36		-	- 3.2			- 1.1	
			0/ 5	4.6		5	-	0.52		0.44		- 1			-	0.36
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		-	- 0.9			
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		-	- 2.4			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA			
			0/10	0.5		10	1.6		1.3	2.6		0.9				
			0/15	1.5		15	4.2		3.4	6.8		2.4				
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36				
			0/10	0.5		10	1.3		1.1	2.6		0.9				
			0/15	1.5		15	3.6		3.0	6.8		2.4				
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A		
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1			
C _I	Input Capacitance			Any Input						5	7.5			pF		

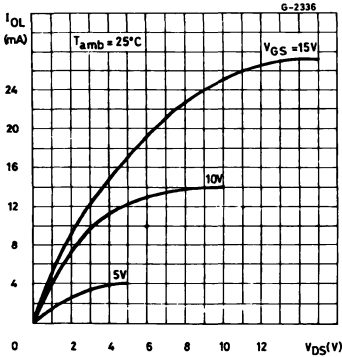
* T_{Low} = - 55°C for HCC device : - 40°C for HCF device* T_{High} = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. width V_{DD} = 5V, 2V min. width V_{DD} = 10V, 2.5V min. width V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

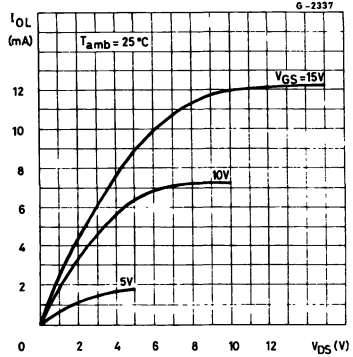
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t_{PLH} , t_{PHL}	Propagation Delay Time Decode Out		5		325	650	ns
			10		135	270	
			15		85	170	
	Carry Out		5		300	600	ns
			10		125	250	
			15		80	160	
t_{THL} , t_{TLH}	Transition Time Carry Out or Decoded Out Line		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}^*	Maximum Clock Input Frequency		5	2.5	5	5	MHz
			10	5	10		
			15	5.5	11		
t_w	Minimum Clock Pulse Width		5		100	200	ns
			10		45	90	
			15		30	60	
t_r , t_f	Clock Input Rise or Fall Time		5	Unlimited			μs
			10				
			15				
t_{setup}	Data Setup Time Minimum Clock Inhibit		5		115	230	ns
			10		50	100	
			15		35	7.5	
RESET OPERATION							
t_{PLH} , t_{PHL}	Propagation Delay Time Carry Out or Decode Out Lines		5		265	530	ns
			10		115	230	
			15		85	170	
t_w	Minimum Reset Pulse Width		5		130	260	ns
			10		55	110	
			15		30	60	
t_{rem}	Minimum Reset Removal Time		5		200	400	ns
			10		140	280	
			15		75	150	

* Measured with respect to carry output line.

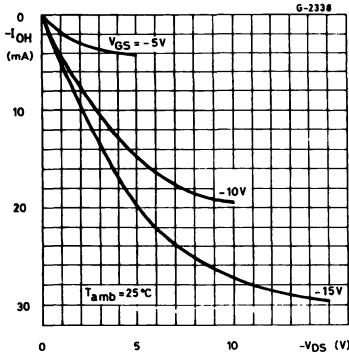
Typical Output Low (sink) Current Characteristics.



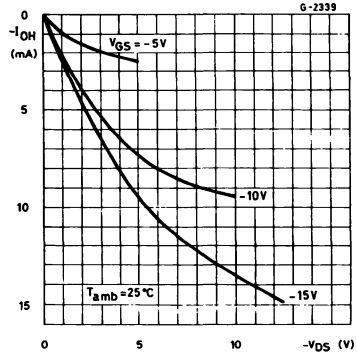
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

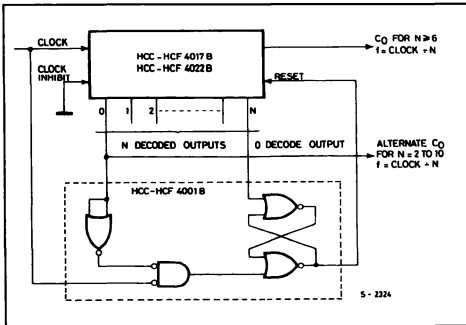


Minimum Output High (source) Current Characteristics.



TYPICAL APPLICATIONS

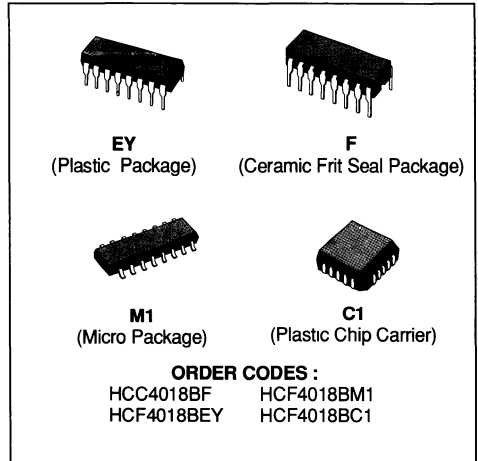
Divide by N Counter ($N \leq 10$) with N Decoded Outputs.



When the N^{th} decoded output is reached (N^{th} clock pulse) the S-R flip-flop (constructed from two NOR gates of the HCC/HCF4001B) generates a reset pulse which clears the HCC/HCF4017B to its zero count. At this time, if the N^{th} decoded output is greater than or equal to 6, the C_{OUT} line goes high to clock the next HCC/HCF4017B counter section. The "0" decoded output also goes high at this time. Coincidence of the clock low and decoded "0" output high resets the S-R flip flop to enable the HCC/HCF4017B. If the N^{th} decoded output is less than 6, the C_{OUT} line will not go high and, therefore, cannot be used. In this case "0" decoded output may be used to perform the clocking function for the next counter.

PRESETTABLE DIVIDE-BY-N COUNTER

- MEDIUM SPEED OPERATION - 10MHz (typ.) AT $V_{DD} - V_{SS} = 10V$
- FULLY STATIC OPERATION
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



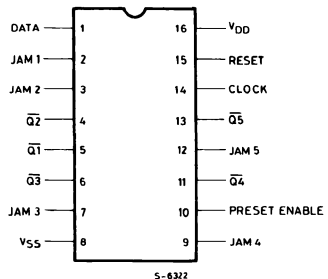
DESCRIPTION

The **HCC4018B** (extended temperature range) and **HCF4018B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

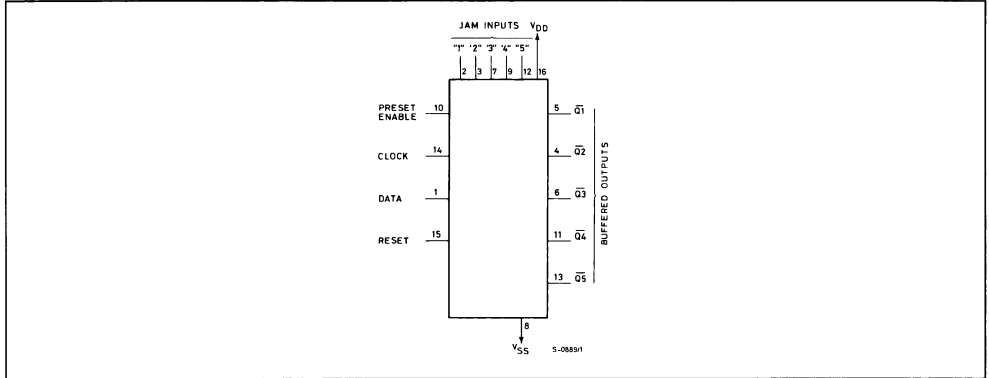
The **HCC/HCF4018B** types consist of 5 Johnson-Counter stages, buffered Q outputs from each stage, and counter preset control gating. CLOCK, RESET, DATA, PRESET ENABLE, and 5 individual JAM inputs are provided. Divide by 10, 8, 6, 4, or 2 counter configurations can be implemented by feeding the Q5, Q4, Q3, Q2, Q1 signals, respectively, back to the DATA input.

Divide-by-9, 7, 5, or 3 counter configurations can be implemented by the use of a **HCC/HCF4011B** gate package to properly gate the feedback connection to the DATA input. Divide-by-functions greater than 10 can be achieved by use of multiple **HCC/HCF4018B** units. The counter is advanced one count at the positive clock-signal transition. Schmitt Trigger action on the clock line permits unlimited clock rise and fall times. A high RESET signal clears the counter to an all-zero condition. A high PRESENT-ENABLE signal allows information on the JAM inputs to preset the counter. Anti-lock gating is provided to assure the proper counting sequence.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

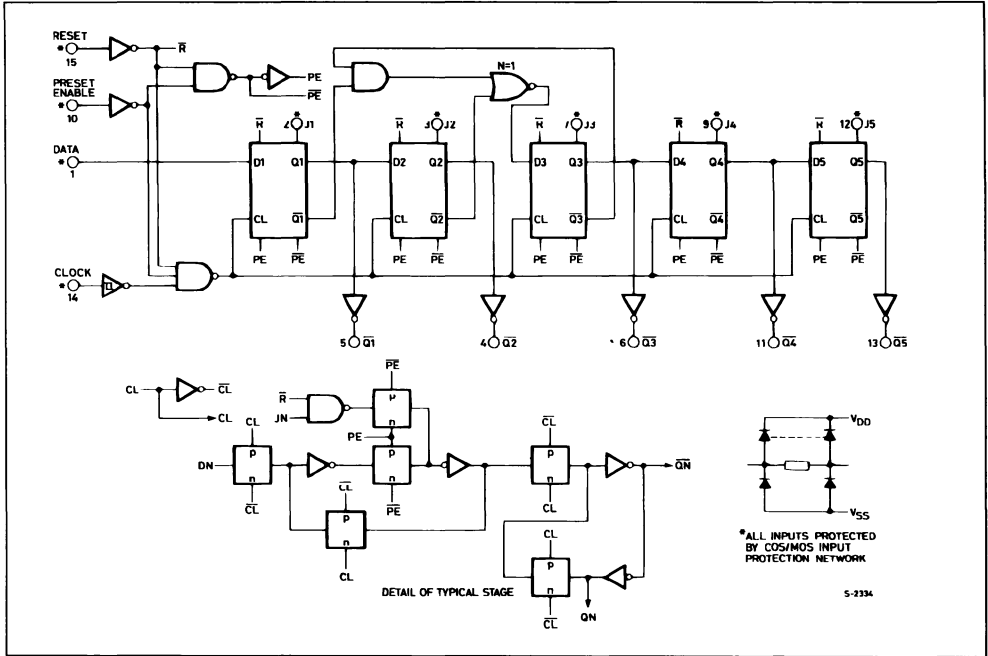
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

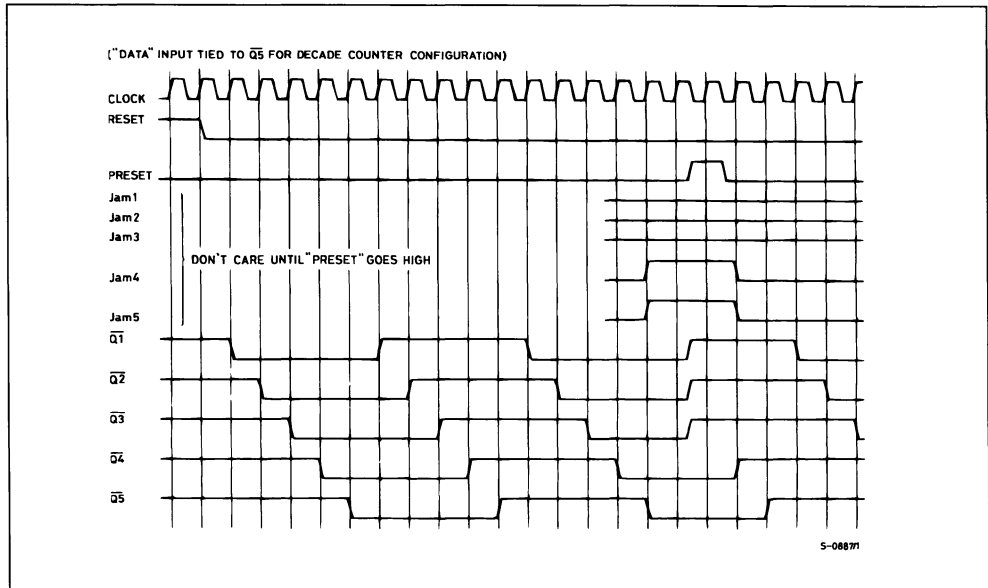
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$

LOGIC DIAGRAM



TIMING DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (under recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance			Any Input					5	7.5			μ F	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device

* T_{High} = +125°C for HCC device : + 85°C for HCF device.

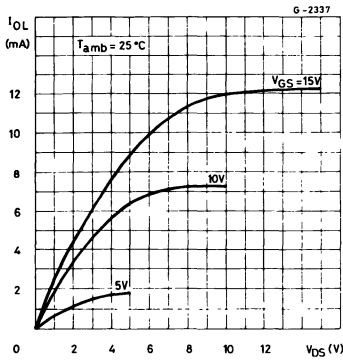
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

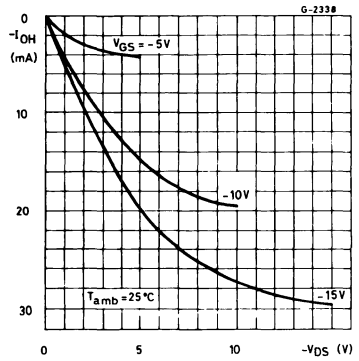
Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
t_{PLH} , t_{PHL}	Propagation Delay Time		5		200	400	ns
			10		90	180	
			15		65	130	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}	Maximum Clock Input Frequency		5	3	6		MHz
			10	7	14		
			15	8.5	17		
t_w	Clock Input Width		5	160	80		ns
			10	70	35		
			15	50	25		
t_r , t_f	Clock Input Rise or Fall Time		5	Unlimited			μs
			10				
			15				
t_{setup}	Data Input Set-up Time		5	40	20		ns
			10	12	6		
			15	6	3		
t_H	Data Input Hold-time		5	140	70		ns
			10	80	40		
			15	60	30		
PRESET* OR RESET OPERATION							
t_{PLH} , t_{PHL}	Propagation Delay Time (reset or reset to Q)		5		275	550	ns
			10		125	250	
			15		90	180	
t_w	Preset or Reset Pulse Width		5	160	80		ns
			10	70	35		
			15	50	25		
t_{rem}	Preset or Reset Removal Time		5	80	40		ns
			10	30	15		
			15	20	10		

* At PRESET ENABLE OR JAM inputs

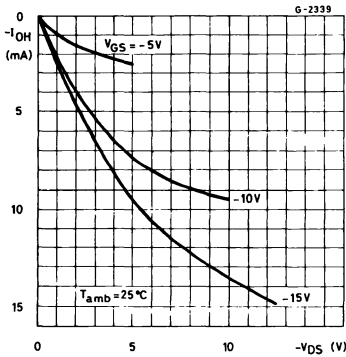
Typical Output Low (sink) Current Characteristics.



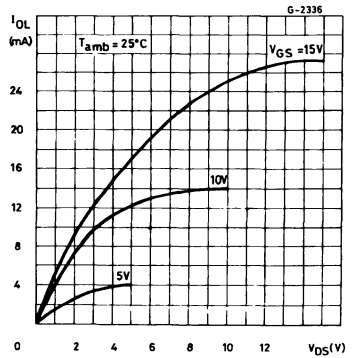
Typical Output high (source) Current Characteristics.



Minimum Output High (source) Current Characteristics.

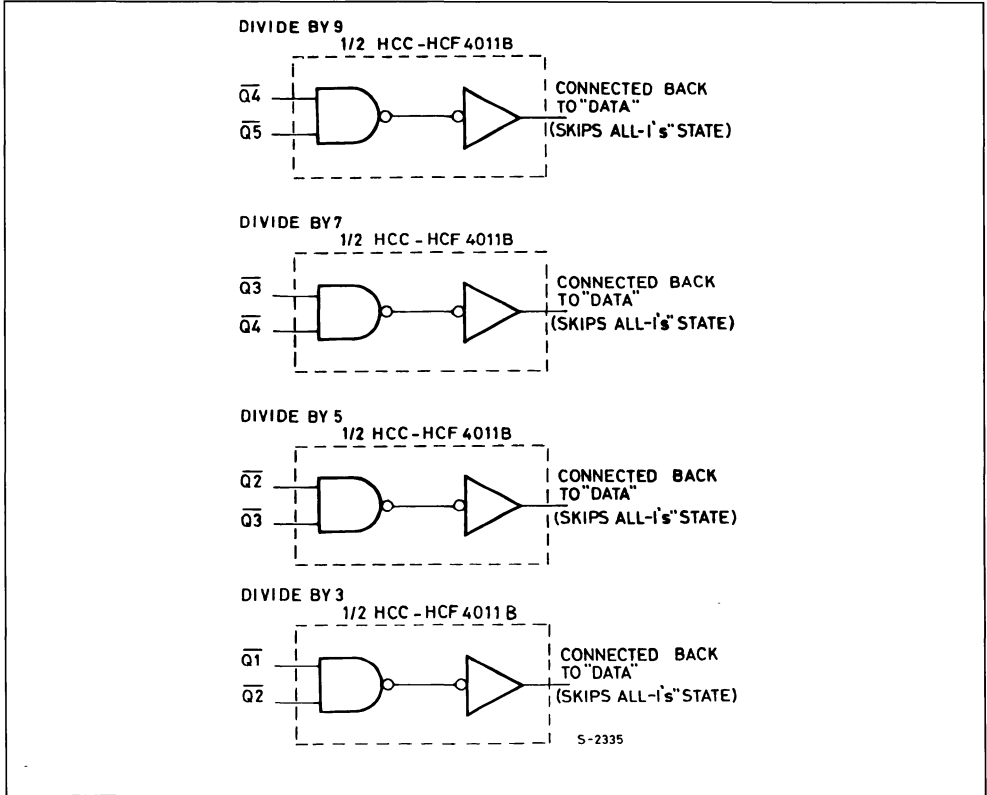


typical Output low (sink) Current Characteristics.



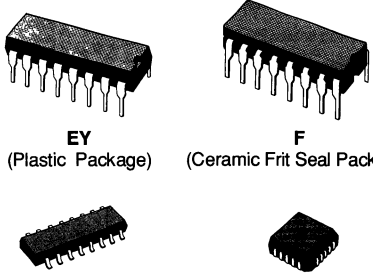
TYPICAL APPLICATIONS

External connections for divide by 10, 9, 8, 7, 6, 5, 4, 3, 2 operation.



QUAD AND/OR SELECT GATE

- MEDIUM SPEED OPERATION : $t_{PHL} = t_{PLH} = 60\text{ns}$ (typ.) AT $C_L = 50\text{pF}$, $V_{DD} = 10\text{V}$
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY (Plastic Package) **F** (Ceramic Frit Seal Package)

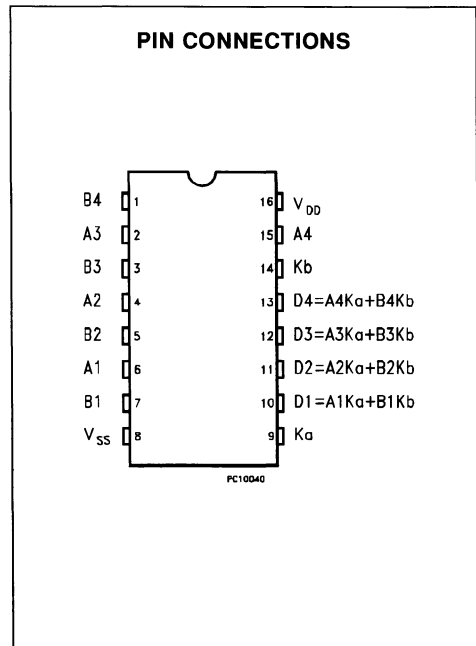
M1 (Micro Package) **C1** (Plastic Chip Carrier)

ORDER CODES :
HCC4019BF HCF4019BM1
HCF4019BEY HCF4019BC1

DESCRIPTION

The **HCC4019B** (extended temperature range) and **HCF4019B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4019B** types are comprised of four AND/OR select gate configurations, each consisting of two 2-input AND gates driving a single 2-input OR gate. Selection is accomplished by control bits K_a and K_b . In addition to selection of either channel A or channel B information, the control bits can be applied simultaneously to accomplish the logical A+B function.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200	mW
		100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T_{stg}	Storage Temperature	- 65 to + 150	°C

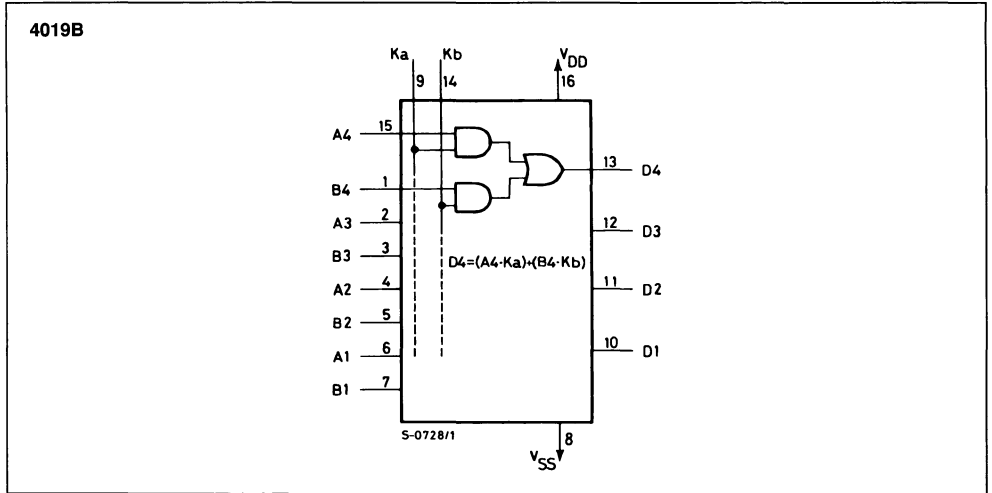
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS



TRUTH TABLE

Ka	Kb	A_n	B_n	DN
1	X	1	X	1
1	X	0	X	0
X	1	X	1	1
X	1	X	0	0
0	0	X	X	0

X = Don't care

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance	All A and B Inputs								5	7.5		pF	
		Ka and Kb Inputs								10	15		pF	

* T_{Low}= - 55°C for HCC device ; - 40°C for HCF device.

* T_{High}= + 125°C for HCC device + 85°C for HCF device

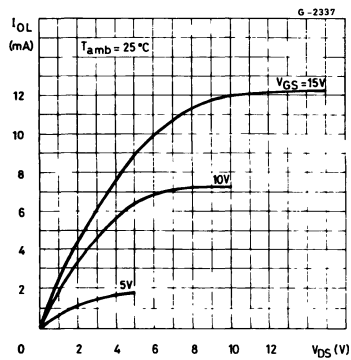
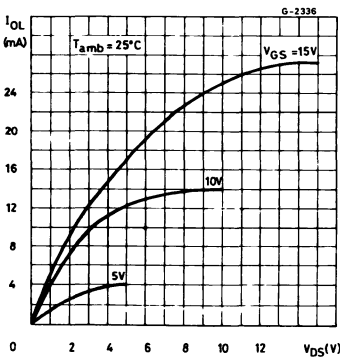
The Noise Margin for both "1" and "0" level is : 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		150	300	ns
			10		60	120	
			15		50	100	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

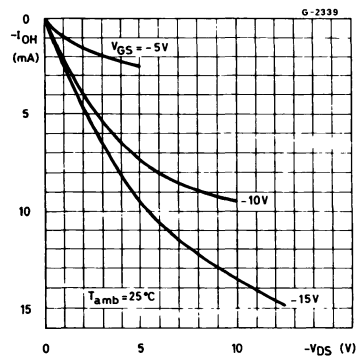
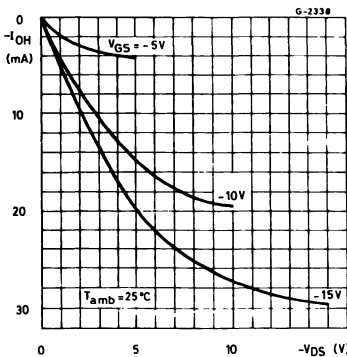
Typical Output Low (sink) Current Characteristics.

Minimum Output Low (sink) Current Characteristics.

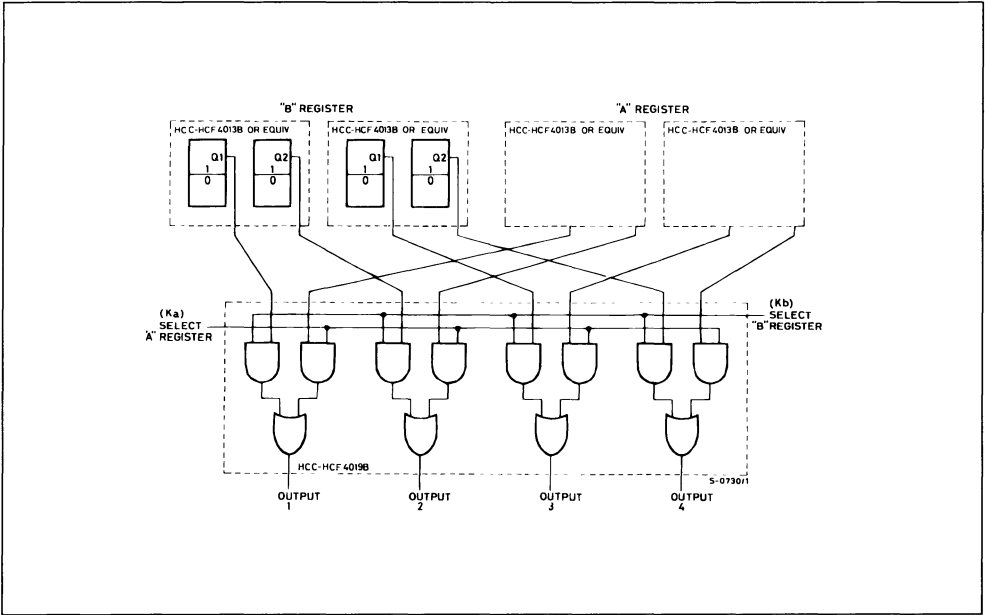


Typical Output High (source) Current Characteristics.

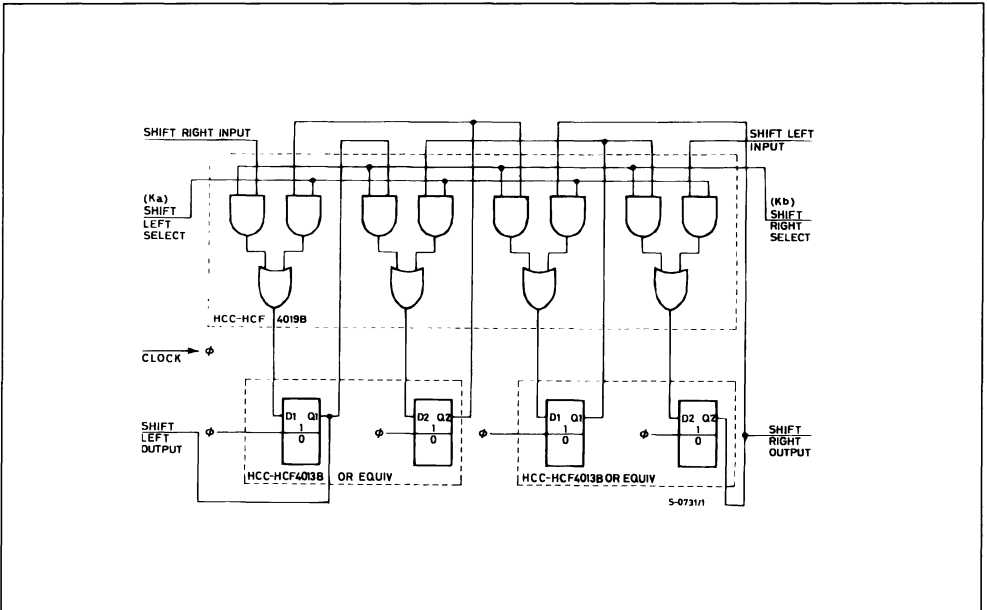
Minimum Output High (source) Current Characteristics.



TYPICAL APPLICATIONS
AND-OR SELECTED GATING.

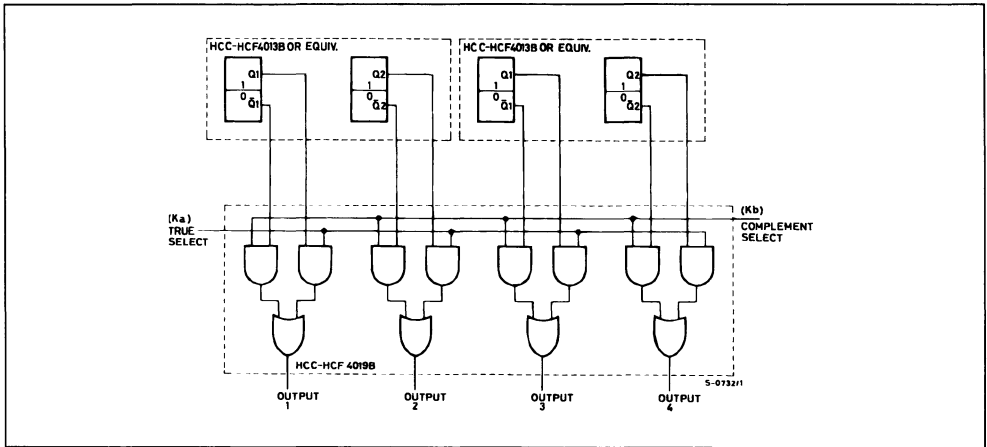


SHIFT LEFT SHIFT RIGHT REGISTER.

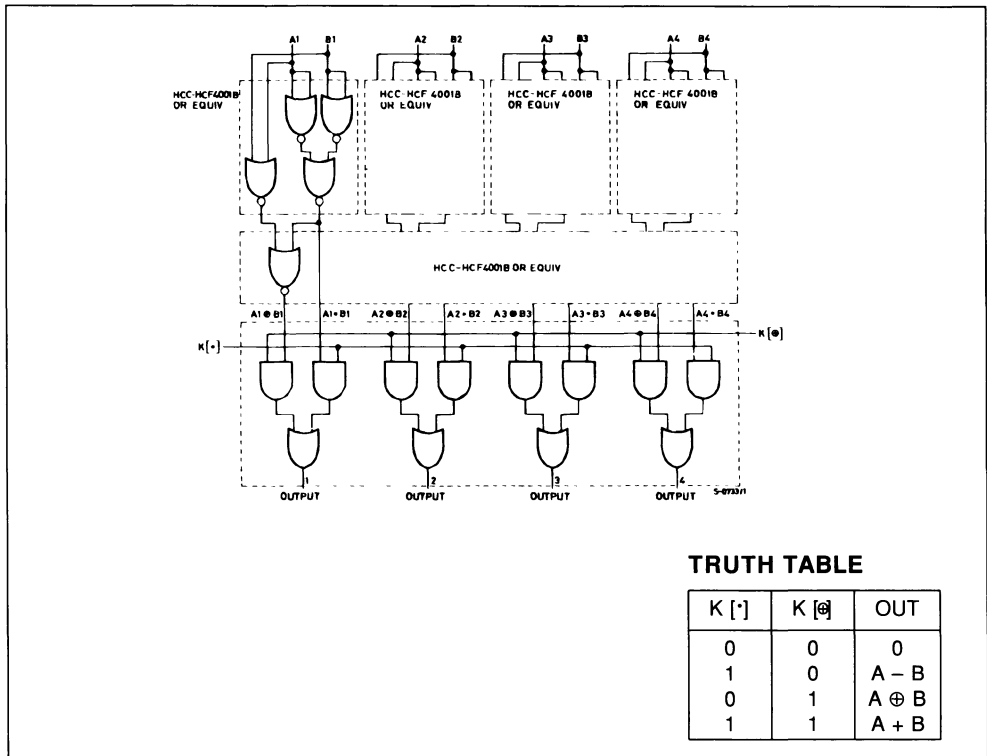


TYPICAL APPLICATIONS (continued)

TRUE COMPLEMENT SELECTOR.



AND-OR EXCLUSIVE-OR SELECTOR.

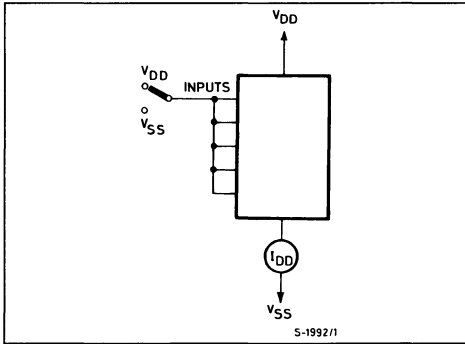


TRUTH TABLE

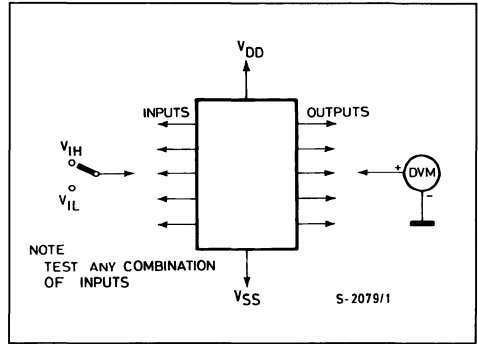
K [•]	K [⊕]	OUT
0	0	0
1	0	A - B
0	1	A ⊕ B
1	1	A + B

TEST CIRCUITS

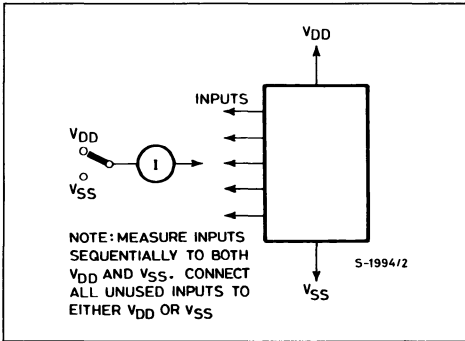
Quiescent Device Current.



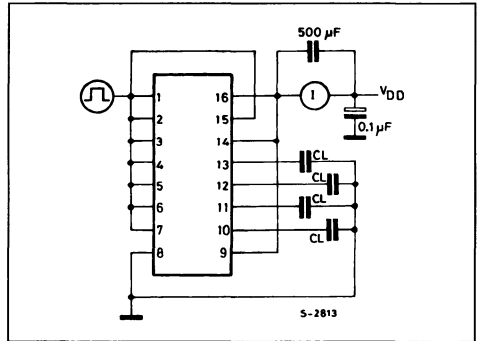
Input Voltage.



Input Leakage Current.



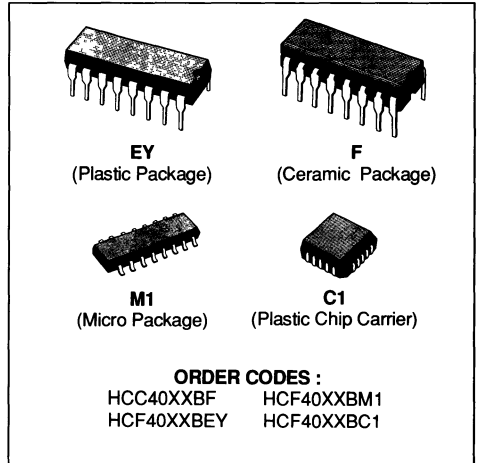
Dynamic Power Dissipation.



RIPPLE-CARRY BINARY COUNTER/DIVIDERS

4020B - 14 STAGE
4024B - 7 STAGE
4040B - 12 STAGE

- MEDIUM-SPEED OPERATION
- FULLY STATIC OPERATION
- COMMON RESET
- BUFFERED INPUTS AND OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

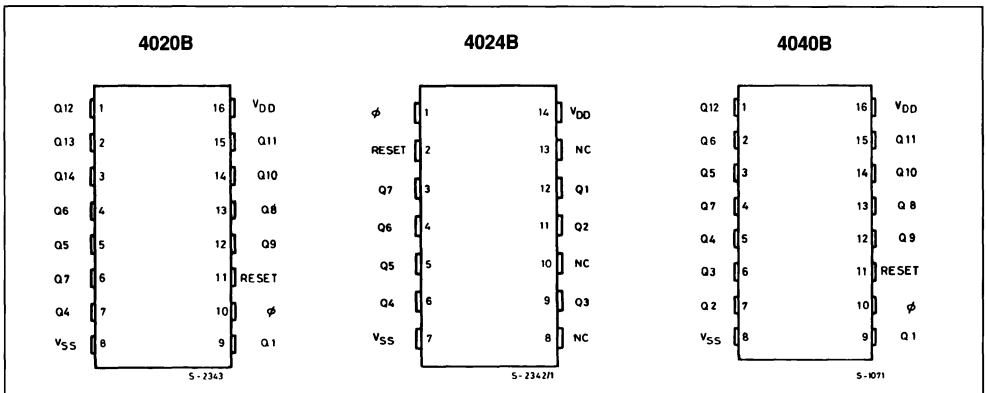


DESCRIPTION

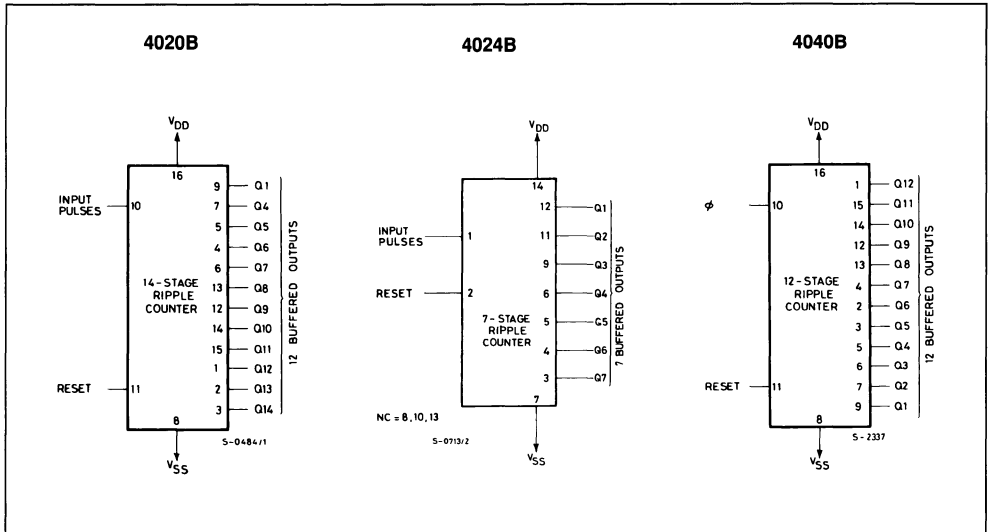
The **HCC4XXXB** (extended temperature range) and **HCF4XXXB** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line for **4024B** and 16-lead dual in-line for **4020B**, **4040B** plastic or ceramic package and plastic micropackage.

The **HCC/HCF4020B**, **4024B**, and **4040B** are ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of a counter advances one count on the negative transition of each input pulse; a high level on the RESET line resets the counter to its all zeros stage. Schmitt trigger action on the input-pulse line permits unlimited clock rise and fall times. All inputs and outputs are buffered.

PIN CONNECTIONS



FUNCTIONAL DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to V_{DD} + 0.5	V
I_I	DC Input Current (any one input)	± 10	mA
P_{Tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

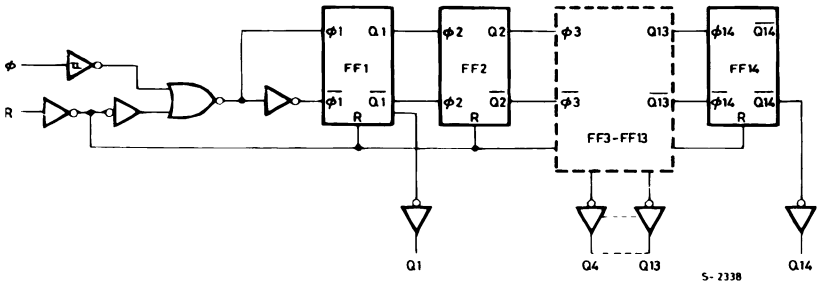
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

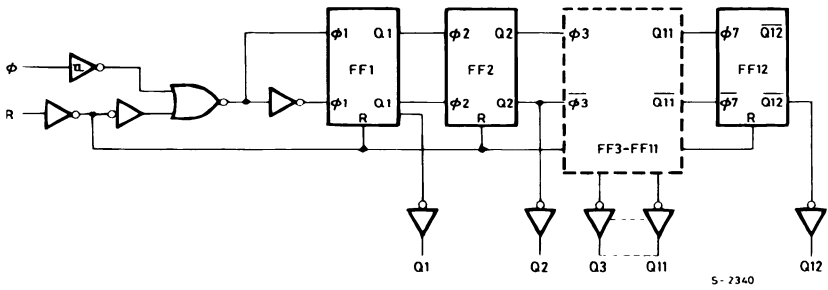
Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$

LOGIC DIAGRAMS

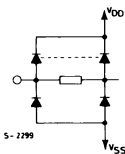
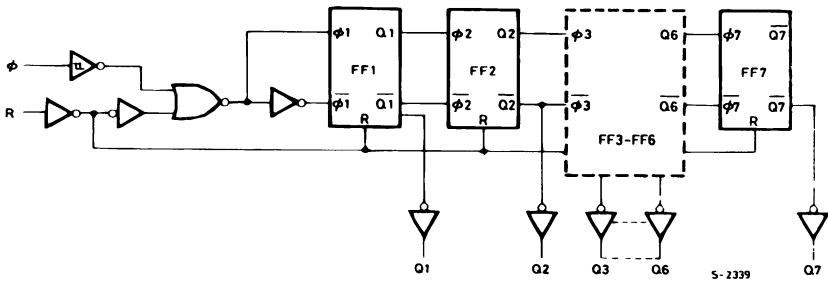
4020B



4040B



4024B



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5	< 1	5	5	4.95		4.95			4.95		V	
		0/10	< 1	10	10	9.95		9.95			9.95			
		0/15	< 1	15	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5	5		0.05			0.05		0.05	V	
		10/0	< 1	10	10		0.05			0.05		0.05		
		15/0	< 1	15	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low}= - 55°C for HCC device : - 40°C for HCF device.

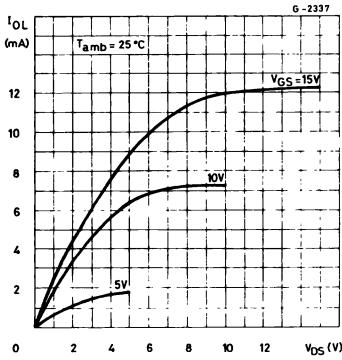
* T_{High}= + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

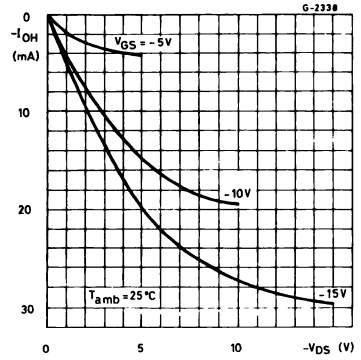
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns).

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
INPUT-PULSE OPERATION							
t_{PLH}, t_{PHL}	Propagation Delay Time (\emptyset to Q1 Out)		5		180	360	ns
			10		80	160	
			15		65	130	
t_{PLH}, t_{PHL}	Propagation Delay Time Q_n to Q_{n+1}		5		100	200	ns
			10		40	80	
			15		30	60	
t_{TLH}, t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_w	Minimum Input Pulse Width		5		70	140	ns
			10		30	60	
			15		20	40	
t_r, t_f	Input Pulse Rise and Fall Time		5	Unlimited			μs
			10				
			15				
f_{max}	Maximum Clock Input Frequency		5	3.5	7		MHz
			10	8	16		
			15	12	24		
RESET OPERATION							
t_{PHL}	Propagation Delay Time		5		140	280	ns
			10		60	120	
			15		50	100	
t_w	Minimum Reset Pulse Width		5		100	200	ns
			10		40	80	
			15		30	60	
t_{rem}	Reset Removal Time		5		175	350	ns
			10		75	150	
			15		50	100	

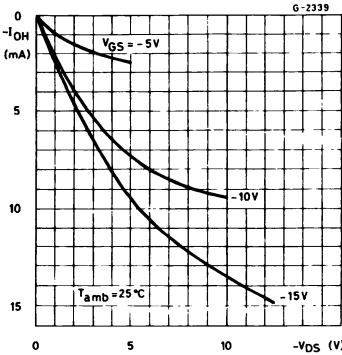
Minimum Output Low (sink) Current Characteristics.



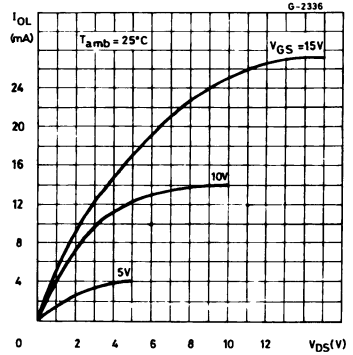
Typical Output Low (source) Current Characteristics.



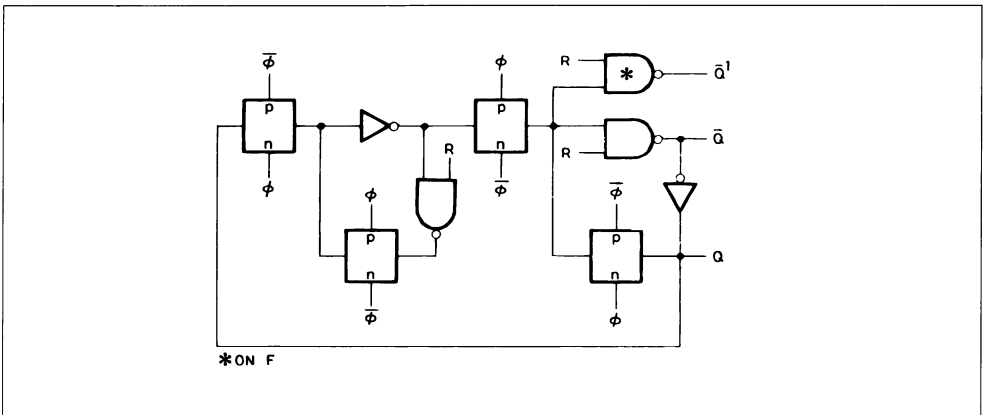
Minimum Output High (source) Current Characteristics.



Typical Output High (sink) Current Characteristics.



Details of Typical Flip-flop Stage.



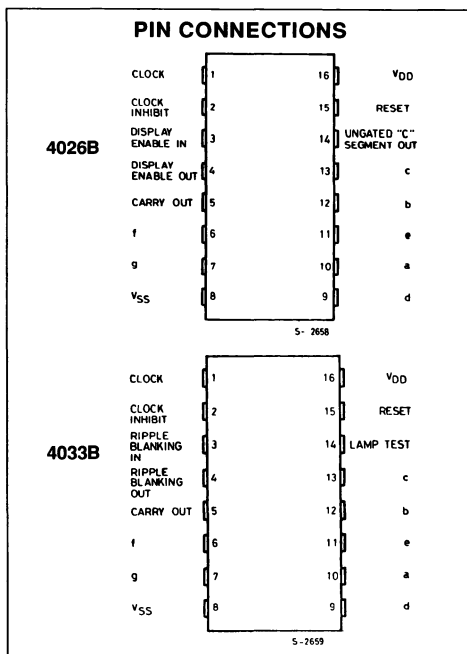
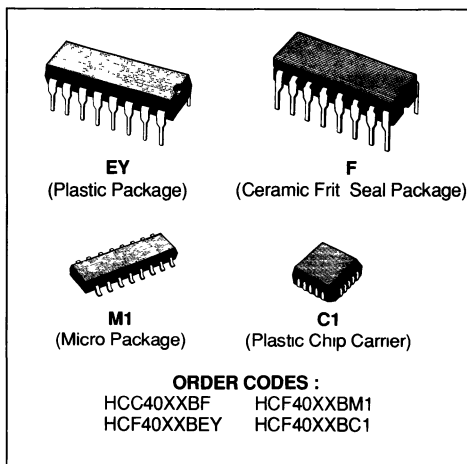
DECADE COUNTERS/DIVIDERS WITH DECODED 7-SEGMENT DISPLAY OUTPUTS

WITH; DISPLAY ENABLE 4026B RIPPLE BLANKING 4033B

- COUNTER AND 7-SEGMENT DECODING IN ONE PACKAGE
- EASILY INTERFACED WITH 7-SEGMENT DISPLAY TYPES
- FULLY STATIC COUNTER OPERATION : DC TO 6MHz (typ.) AT $V_{DD} = 10V$
- IDEAL FOR LOW-POWER DISPLAYS
- DISPLAY ENABLE OUTPUT - 4026B
- "RIPPLE BLANKING" AND LAMP TEST - 4033B
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4026B/4033B** (extended temperature range) and **HCF4026B/4033B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4026B** and **HCC/HCF4033B** each consist of a 5-stage Johnson decade counter and an output decoder which converts the Johnson code to a 7-segment decoded output for driving one stage in a numerical display. These devices are particularly advantageous in display applications where low power dissipation and/or low package count are important. Inputs common to both types are CLOCK, RESET, & CLOCK INHIBIT ; common outputs are CARRY OUT and the seven decoded outputs (a, b, c, d, e, f, g). Additional inputs and outputs for the **HCC/HCF4026B** include DISPLAY ENABLE input and DISPLAY ENABLE and UNGATED "C-SEGMENT" outputs. Signals peculiar to the **HCC/HCF4033B** are RIPPLE-BLANKING INPUT AND LAMP TEST INPUT and a RIPPLE-BLANKING OUTPUT. A high RESET signal clears the



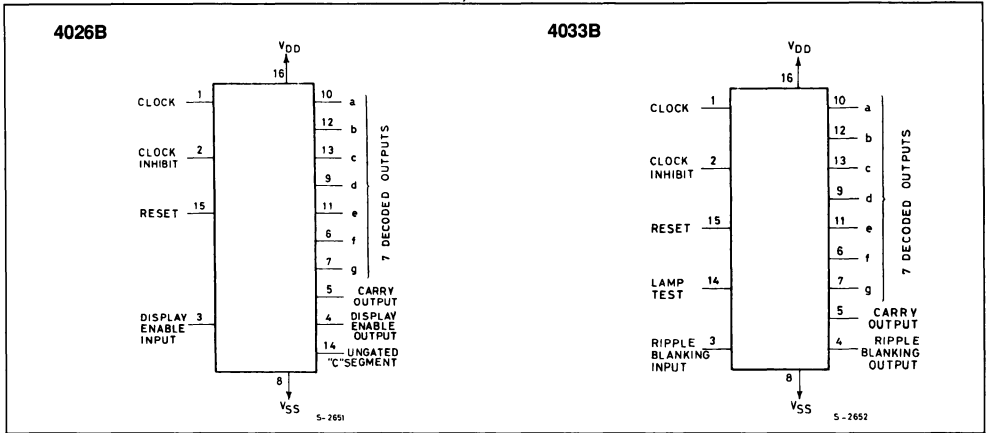
decade counter to its zero count. The counter is advanced one count at the positive clock signal transition if the CLOCK INHIBIT signal is low. Counter advancement via the clock line is inhibited when the CLOCK INHIBIT signal is high. Antilock gating is provided on the JOHNSON counter, thus assuring proper counting sequence. The CARRY-OUT (C_{out}) signal completes one cycle every ten CLOCK INPUT cycles and is used to clock the succeeding decade directly in a multi-decade counting chain. The seven decoded outputs (a, b, c, d, e, f, g) illuminate the proper segments in a seven segment display device used for representing the decimal numbers 0 to 9. The 7-segment outputs go high on selection in the **HCC/HCF4033B** ; in the **HCC/HCF4026B** these outputs go high only when the DISPLAY ENABLE IN is high.

HCC/HCF4026B - When the DISPLAY ENABLE IN is low the seven decoded outputs are forced low regardless of the state of the counter. Activation of the display only when required results in significant power savings. This system also facilitates implementation of display-character multiplexing. The CARRY OUT and UNGATED "C-SEGMENT" signals are not gated by the DISPLAY ENABLE and therefore are available continuously. This feature is a requirement in implementation of certain divider functions such as divide-by-60 and divide-by-12.

HCC/HCF4033B - The **HCC/HCF4033B** has provisions for automatic blanking of the non-significant zeros in a multi-digit decimal number which results in an easily readable display consistent

with normal writing practice. For example, the number 0050.07000 in an eight digit display would be displayed as 50.07. Zero suppression on the integer side is obtained by connecting the RBI terminal of the **HCC/HCF4033B** associated with the most significant digit in the display to a low-level voltage and connecting the RBO terminal of that stage to the RBI terminal of the **HCC/HCF4033B** in the next-lower significant position in the display. This procedure is continued for each succeeding **HCC/HCF4033B** on the integer side of the display. On the fraction side of the display the RBI of the **HCC/HCF4033B** associated with the least significant bit is connected to a low-level voltage and the RBO of that **HCC/HCF4033B** is connected to the RBI terminal of the **HCC/HCF4033B** in the next more-significant-bit position. Again, this procedure is continued for all **HCC/HCF4033B's** on the fraction side of the display. In a purely fractional number the zero immediately preceding the decimal point can be displayed by connecting the RBI of that stage to a high level voltage (instead of to the RBO of the next more-significant-stage). For example : optional zero → 0.7346. Likewise, the zero in a number such as 763.0 can be displayed by connecting the RBI of the **HCC/HCF4033B** associated with it to a high-level voltage. Ripple blanking of non-significant zeros provides an appreciable savings in display power. The **HCC/HCF4033B** has a LAMP TEST input which, when connected to a high-level voltage, overrides normal decoder operation and enables a check to be made on possible display malfunctions by putting the seven outputs in the high state.

FUNCTIONAL DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}$ C $^{\circ}$ C
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}$ C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

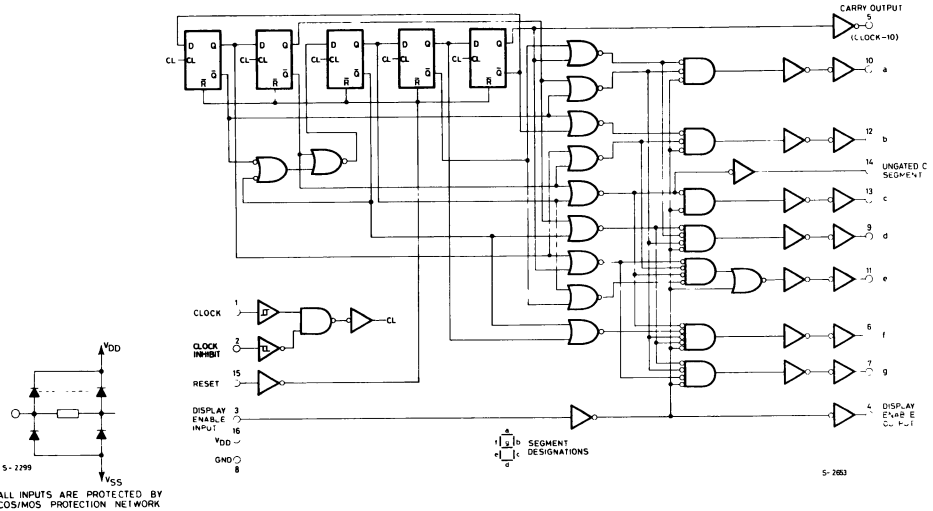
* All voltages values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

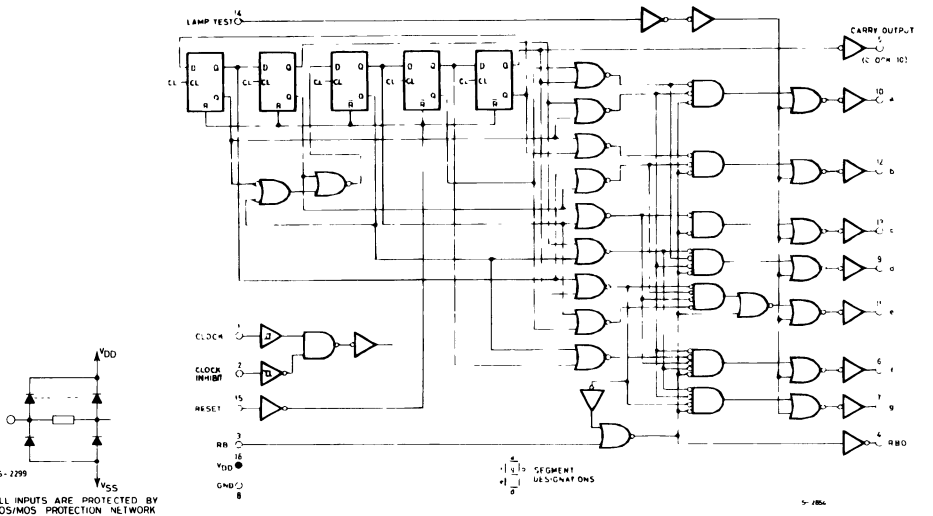
Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}$ C $^{\circ}$ C

LOGIC DIAGRAMS

4026B

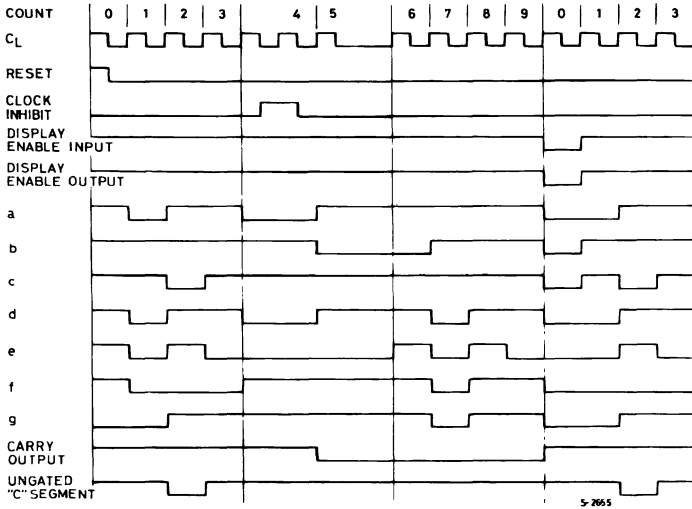


4033B

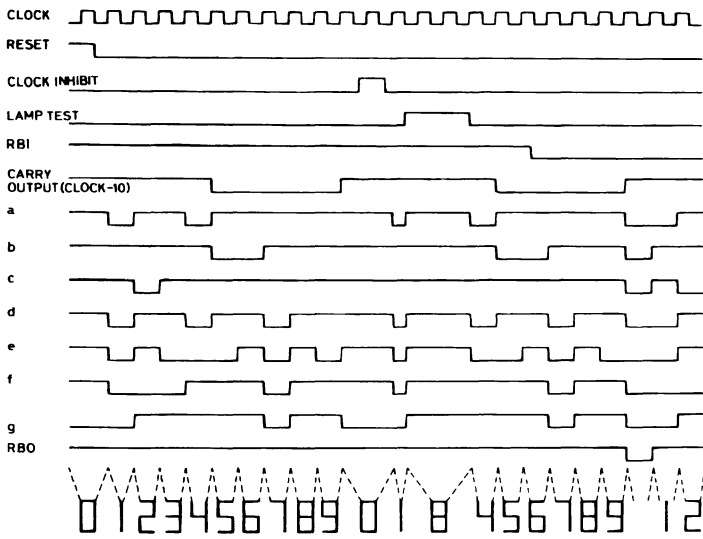


TIMING DIAGRAMS

4026B



4033B



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
		0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

(*) T_{Low} = - 55°C for HCC device . - 40°C for HCF device

T_{High} = + 125°C for HCC device + 85°C for HCF device

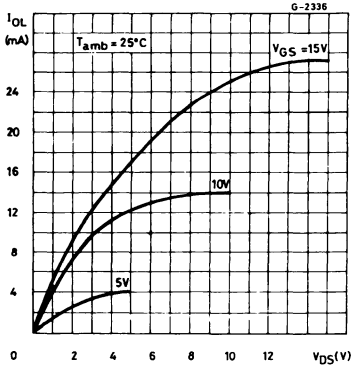
The Noise Margin for both "1" and "0" level is . 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

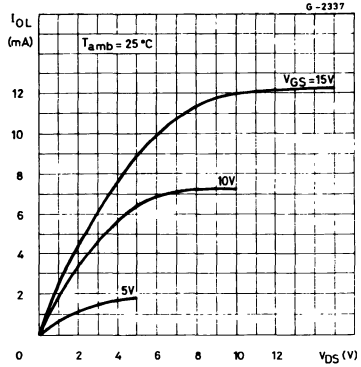
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t_{PLH}, t_{PHL}	Propagation Delay Time Carry Out Line		5		250	500	ns
			10		100	200	
			15		75	150	
t_{PLH}, t_{PHL}	Propagation Delay Time Decode Out Lines		5		350	700	ns
			10		125	250	
			15		90	180	
t_{THL}, t_{TLH}	Transition Time Carry Out Line		5		100	200	ns
			10		50	100	
			15		25	50	
f_{CL}^*	Maximum Clock Input Frequency		5	2.5	5		MHz
			10	5.5	11		
			15	8	16		
t_{WC}	Clock Pulse Width		5		110	270	ns
			10		50	100	
			15		40	80	
t_r, t_f	Clock Input Rise or Fall Time		5	Unlimited			μs
			10				
			15				
RESET OPERATION							
$t_{PLH},$	Propagation Delay Time Carry Out Line		5		275	550	ns
			10		120	240	
			15		80	160	
t_{PLH}, t_{PHL}	Propagation Delay Time Decode Out Lines		5		300	600	ns
			10		125	250	
			15		90	180	
t_{WR}	Reset Pulse Width		5		100	120	ns
			10		50	100	
			15		25	50	
t_{rem}	Reset Removal Time		5		0	30	ns
			10		0	15	
			15		0	10	

* Measured with respect to carry output line.

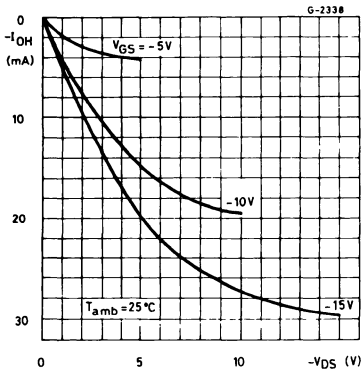
Typical Output Low (sink) Current.



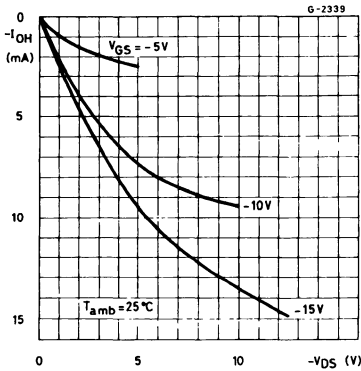
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

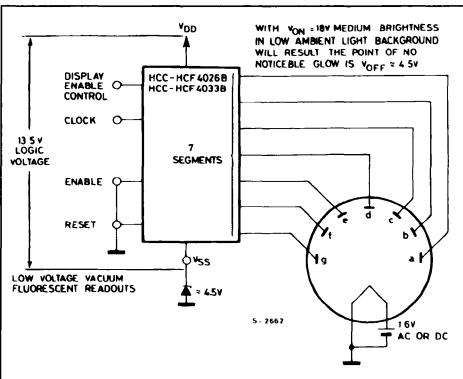


Minimum Output High (source) Current Characteristics.

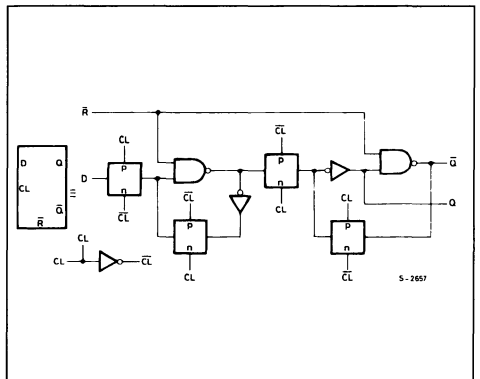


TYPICAL APPLICATIONS

Interfacing with Filament Fluorescent Display.

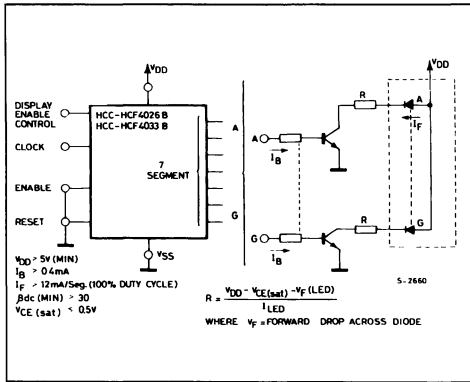


Detail of Typical Flip-flop Stage for Both Types.

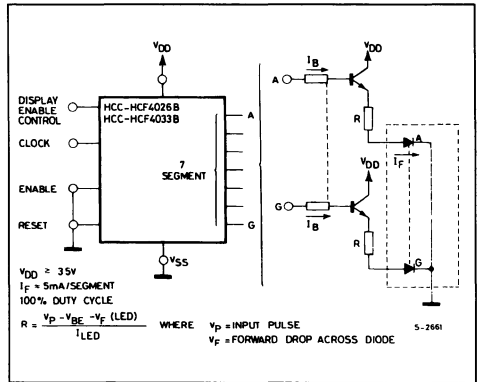


TYPICAL APPLICATIONS (continued)

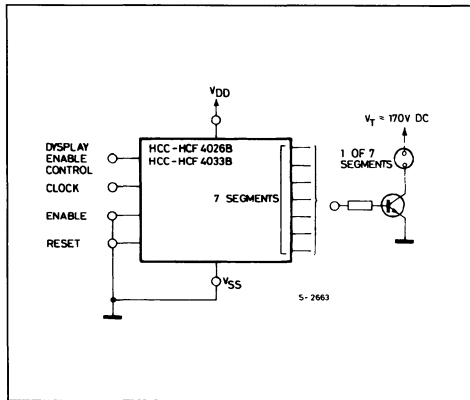
Interfacing with LED Displays (display common anode).



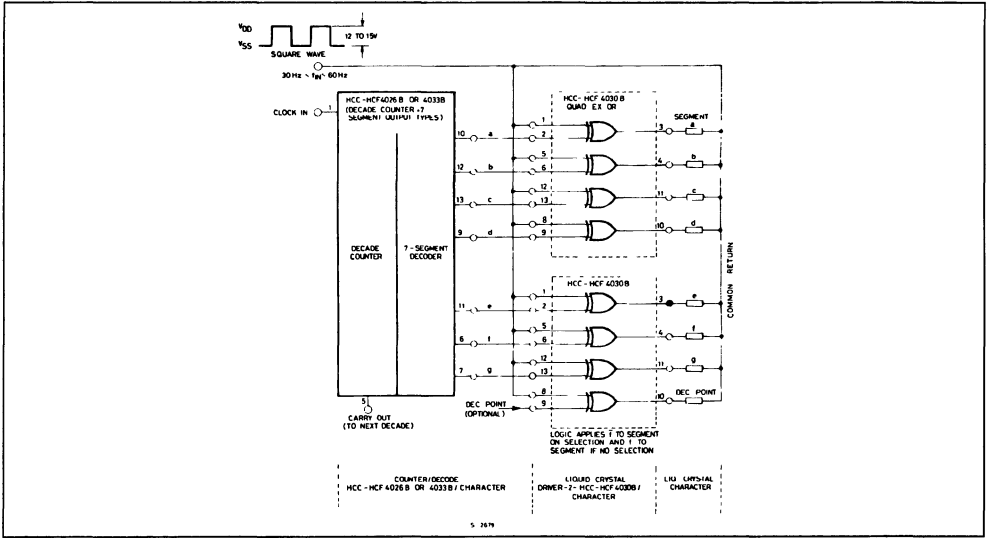
(Display Common Cathode).



Interfacing with NIXIE Tube.

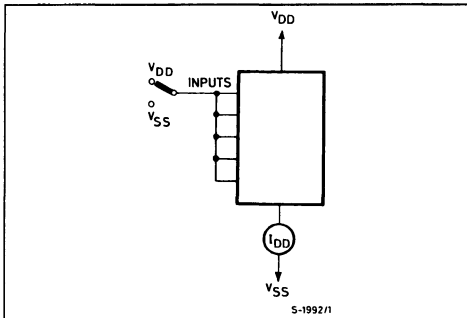


Interfacing with Liquid Crystal Displays.

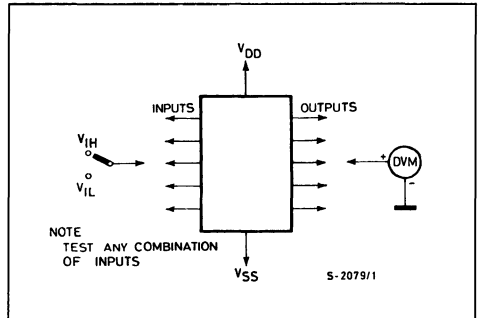


TEST CIRCUITS

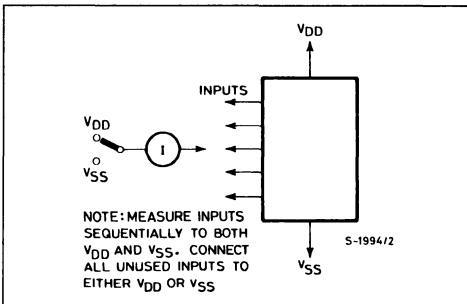
Quiescent Device Current.



Input Voltage.

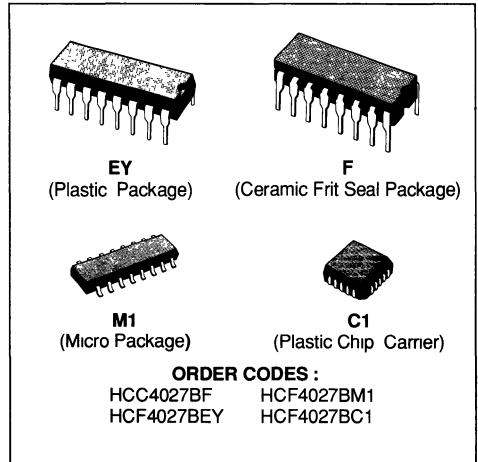


Input Current.



DUAL-J-K MASTER-SLAVE FLIP-FLOP

- SET-RESET CAPABILITY
- STATIC FLIP-FLOP OPERATION - RETAINS STATE INDEFINITELY WITH CLOCK LEVEL EITHER "HIGH" OR "LOW"
- MEDIUM SPEED OPERATION - 16MHz (typ. clock toggle rate at 10V)
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES".



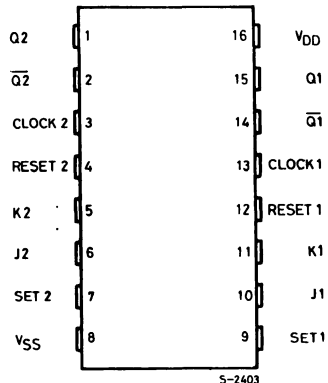
DESCRIPTION

The **HCC4027B** (extended temperature range) and **HCF4027B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

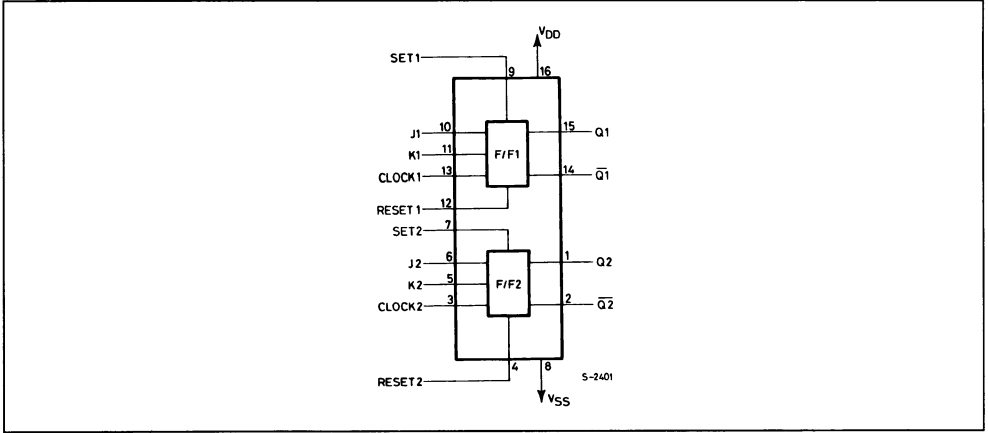
The **HCC/HCF4027B** is a single monolithic chip integrated circuit containing two identical complementary-symmetry J-K master-slave flip-flops. Each flip-flop has provisions for individual J, K, Set, Reset, and Clock input signals, Buffered Q and \bar{Q} signals are provided as outputs. This input-output arrangement provides for compatible operation with the **HCC/HCF4013B** dual D-type flip-flop.

The **HCC/HCF4027B** is useful in performing control, register, and toggle functions. Logic levels present at the J and K inputs along with internal self-steering control the state of each flip-flop ; changes in the flip-flop state are synchronous with the positive-going transition of the clock pulse. Set and reset functions are independent of the clock and are initiated when a high level signal is present at either the Set or Reset input.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

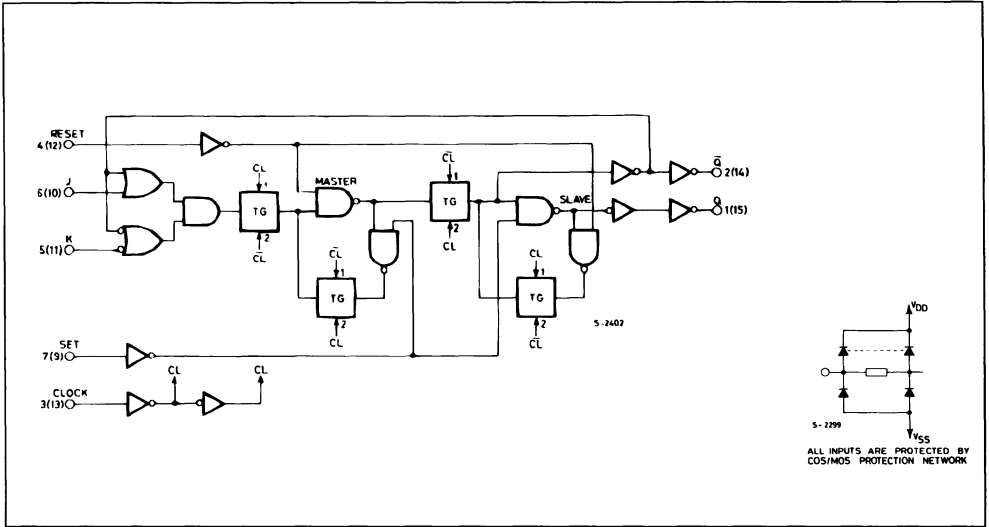
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

LOGIC DIAGRAM AND TRUTH TABLE

ONE OF TWO IDENTICAL J-K FLIP-FLOPS



TRUTH TABLE

Present State				Output	CL ^Δ	Next State		
Inputs			Q			Q	Q̄	
J	K	S	R	Q		Q	Q̄	
1	X	0	0	0	┌	1	0	
X	0	0	0	1	┌	1	0	
0	X	0	0	0	┐	0	1	
X	1	0	0	1	┐	0	1	
X	X	0	0	X	┐			← No Change
X	X	1	0	X	X	1	0	
X	X	0	1	X	X	0	1	
X	X	1	1	X	X	1	1	

LOGIC 1 = HIGH LEVEL
 LOGIC 0 = LOW LEVEL
 Δ - LEVEL CHANGE
 X - DON'T CARE

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit		
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5			1		0.02	1		30	μ A
			0/10			10			2		0.02	2		60	
			0/15			15			4		0.02	4		120	
			0/20			20			20		0.04	20		600	
		HCF Types	0/5			5			4		0.02	4		30	
			0/10			10			8		0.02	8		60	
			0/15			15			16		0.02	16		120	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95			V	
		0/10		< 1	10	9.95		9.95			9.95				
		0/15		< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V		
		10/0		< 1	10		0.05			0.05		0.05			
		15/0		< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V		
			1/9	< 1	10	7		7			7				
			1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V		
			9/1	< 1	10		3			3		3			
			13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA		
			0/5	4.6		5	-0.64		-0.51	-1		-0.36			
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52		-0.44	-1		-0.36			
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA		
			0/10	0.5		10	1.6		1.3	2.6		0.9			
			0/15	1.5		15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36			
			0/10	0.5		10	1.3		1.1	2.6		0.9			
			0/15	1.5		15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18	± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A		
		HCF Types	0/15											15	± 0.3
C _I	Input Capacitance			Any Input					5	7.5			pF		

* T_{Low} = -55°C for HCC device - 40°C for HCF device.

* T_{High} = +125°C for HCC device . + 85°C for HCF device.

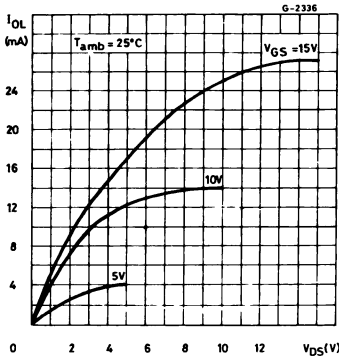
The Noise Margin for both "1" and "0" level is .1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

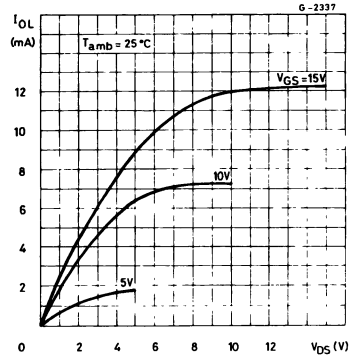
Symbol	Parameter		Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.		
t_{PLH}, t_{PHL}	Propagation Delay Time	Clock to Q or \bar{Q} Outputs	5		150	300	ns	
			10		65	130		
			15		45	90		
t_{PLH}	Propagation Delay Time	Set to Q or Reset to \bar{Q}	5		150	300	ns	
			10		65	130		
			15		45	90		
t_{PHL}	Propagation Delay Time	Set to \bar{Q} or Reset to Q	5		200	400	ns	
			10		85	170		
			15		60	120		
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns	
			10		50	100		
			15		40	80		
t_W	Pulse Width	Clock	5	140	70		ns	
			10	60	30			
			15	40	20			
t_W	Pulse Width	Set or Reset	5	180	90		ns	
			10	80	40			
			15	50	25			
t_r, t_f	Clock Input Rise or Fall Time		5			15	μs	
			10			4		
			15			1		
t_{setup}	Setup Time	Data	5	200	100		ns	
			10	75	35			
			15	50	25			
f_{max}	Maximum Clock Input Frequency *	Toggle Mode	5	3.5	7		MHz	
			10	8	16			
			15	12	24			

* Input $t_r, t_f = 5\text{ns}$.

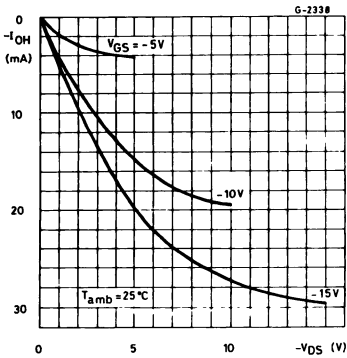
Typical Output Low (sink) Current Characteristics.



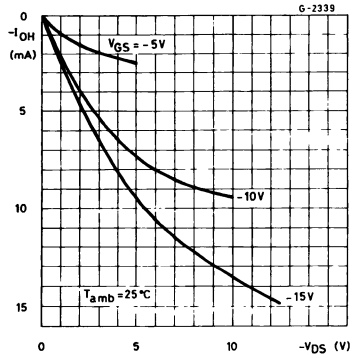
Minimum Output Low (sink) Current Characteristics.



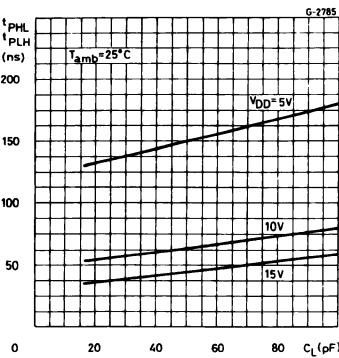
Typical Output High (source) Current Characteristics.



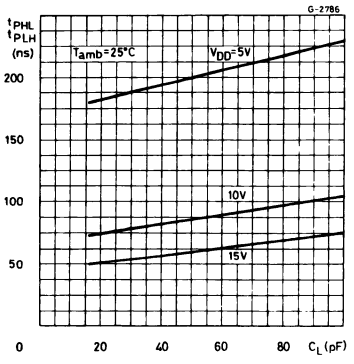
Minimum Output High (source) Current Characteristics.



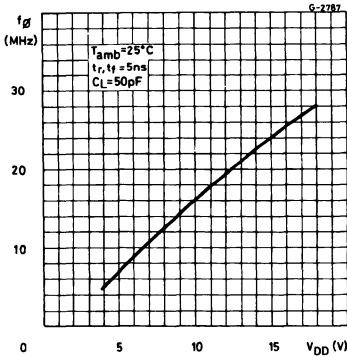
Typical Propagation Delay Time vs. Load Capacitance (CLOCK or SET to Q, CLOCK or RESET to \bar{Q}).



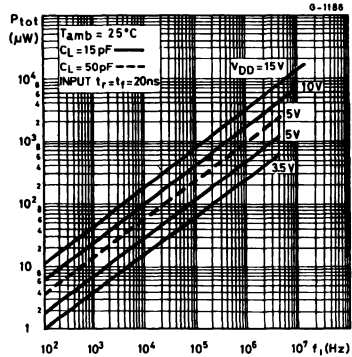
Typical Propagation Delay Time vs. Load Capacitance (SET to \bar{Q} or RESET to Q).



Typical Maximum Clock Frequency vs. Supply Voltage (Toggle Mode).

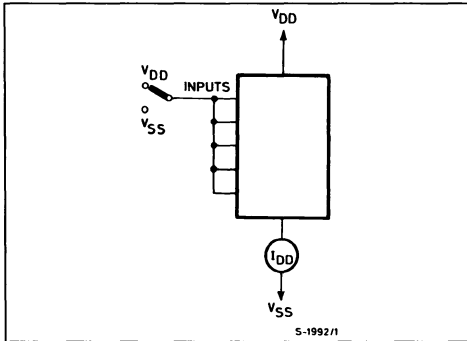


Typical Dynamic Power Dissipation/ Per Device vs. Frequency.

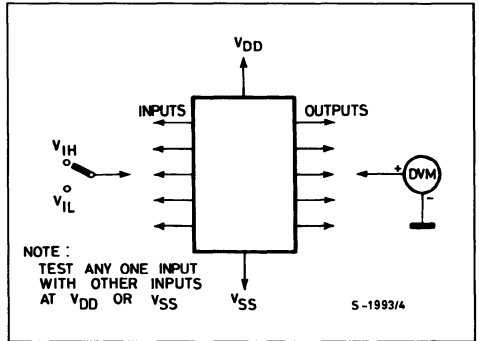


TEST CIRCUITS

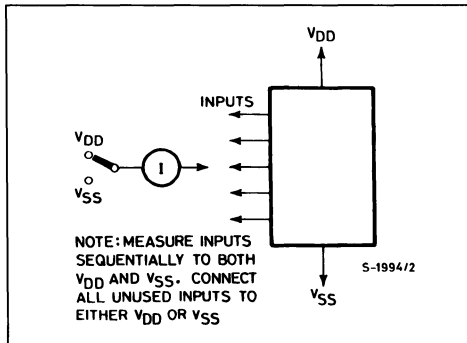
Quiescent Device Current.



Input Voltage.

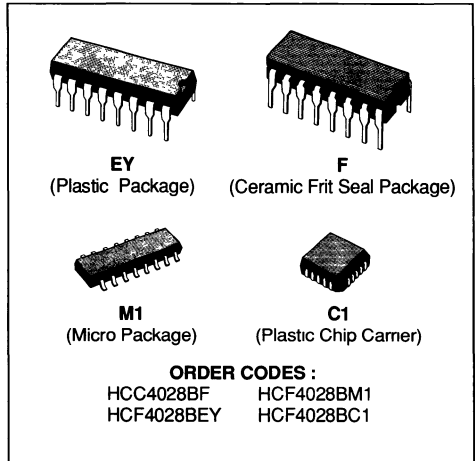


Input Leakage Current.



BCD-TO-DECIMAL DECODER

- BCD-TO-DECIMAL DECODING OR BINARY-TO-OCTAL DECODING
- HIGH DECODED OUTPUT DRIVE CAPABILITY
- "POSITIVE LOGIC" INPUTS AND OUTPUTS : DECODED OUTPUTS GO HIGH ON SELECTION
- MEDIUM-SPEED OPERATION : t_{PHL} , t_{PLH} = 80ns (typ.) @ V_{DD} = 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

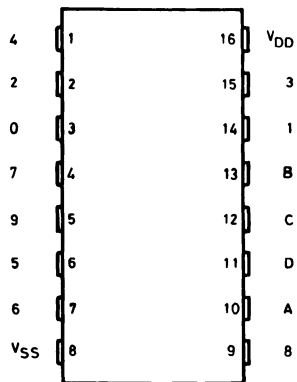


DESCRIPTION

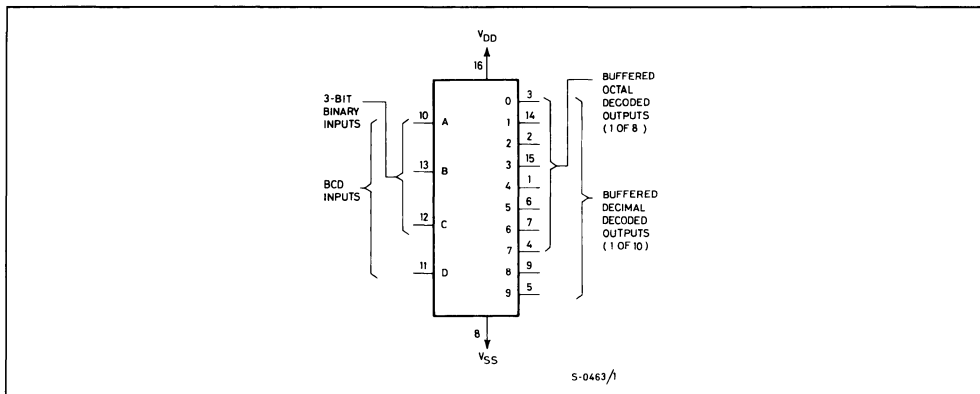
The **HCC4028B** (extended temperature range) and **HCF4028B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4028B** types are BCD-to-decimal or binary-to-octal decoders consisting of buffering on all 4 inputs, decoding-logic gates, and 10 output buffers. A BCD code applied to the four inputs, A to D, results in a high level at the selected one of 10 decimal decoded outputs. Similarly, a 3-bit binary code applied to inputs A through C is decoded in octal code at output 0 to 7 if D = "0". High drive capability is provided at all outputs to enhance dc and dynamic performance in high fan-out applications.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage · HCC Types HCF Types	– 0.5 to + 20 – 0.5 to + 18	V
V_I	Input Voltage	– 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

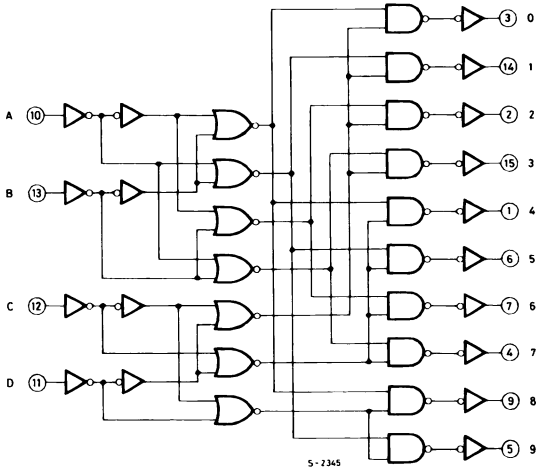
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

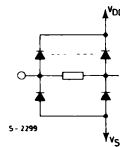
Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAM AND TRUTH TABLE



D	C	B	A	0	1	2	3	4	5	6	7	8	9
0	0	0	0	1	0	0	0	0	0	0	0	0	0
0	0	0	1	0	1	0	0	0	0	0	0	0	0
0	0	1	0	0	0	1	0	0	0	0	0	0	0
0	0	1	1	0	0	0	1	0	0	0	0	0	0
0	1	0	0	0	0	0	0	1	0	0	0	0	0
0	1	0	1	0	0	0	0	0	1	0	0	0	0
0	1	1	0	0	0	0	0	0	0	1	0	0	0
0	1	1	1	0	0	0	0	0	0	0	1	0	0
1	0	0	0	0	0	0	0	0	0	0	0	1	0
1	0	0	1	0	0	0	0	0	0	0	0	0	1
1	0	1	0	0	0	0	0	0	0	0	0	0	0
1	0	1	1	0	0	0	0	0	0	0	0	0	0
1	1	0	0	0	0	0	0	0	0	0	0	0	0
1	1	0	1	0	0	0	0	0	0	0	0	0	0
1	1	1	0	0	0	0	0	0	0	0	0	0	0
1	1	1	1	0	0	0	0	0	0	0	0	0	0

WHERE 1 = HIGH LEVEL



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance	Any Input							5	7.5			pF	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device

* T_{High} = + 125°C for HCC device + 85°C for HCF device

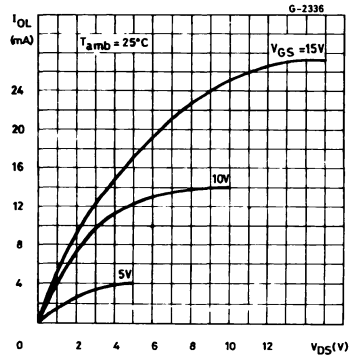
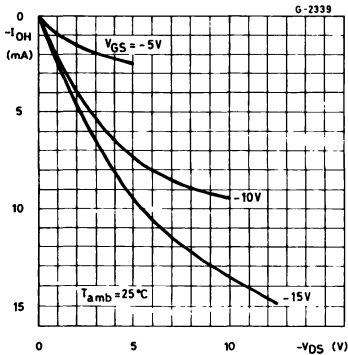
The Noise Margin for both "1" and "0" level is . 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time (clock to "out")		5		175	350	ns
			10		80	160	
			15		60	120	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

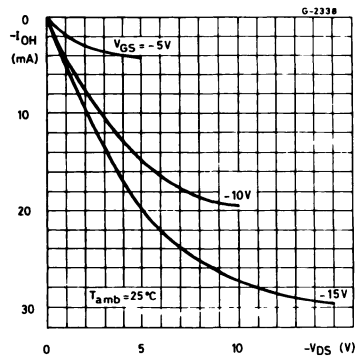
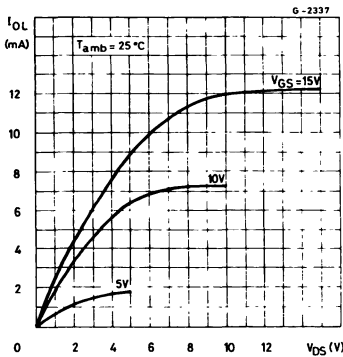
Minimum Output High (source) Current Characteristics.

Typical Output Low (sink) Current.

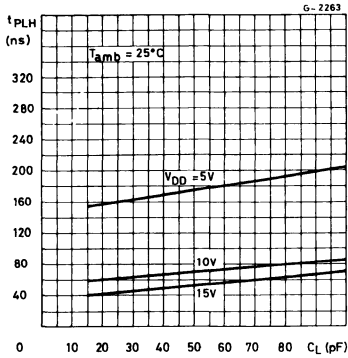


Minimum Output Low (Sink) Current Characteristics.

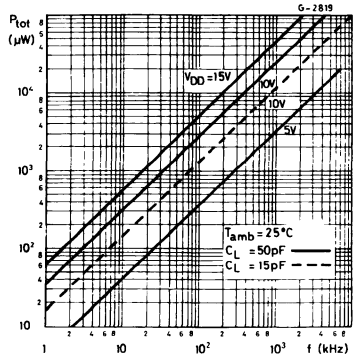
Typical Output High (source) Current Characteristics.



Typical Propagation Delay Time as a Function load Capacitance.



Typical Dynamic Power Dissipation as a Function of Input Frequency .



TYPICAL APPLICATIONS

The circuit shown in fig. 1 converts any 4-bit code to a decimal or hexadecimal code Fig 2 shows a number of codes and the decimal or hexadecimal number in these codes which must be applied to the input pins of the HCC/HCF4028B to select a par-

ticular output. For example : in order to get a "high" on output n8 the input must be either an 8 expressed in 4-bit binary code, a 15 expressed in 4-bit gray code, or a 5 expressed in excess-3code.

Figure 1 : Code Conversion Circuit.

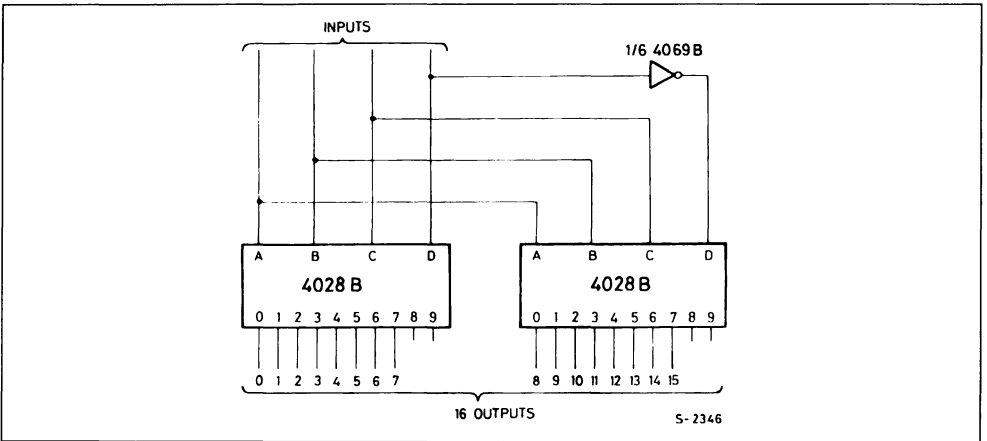


Figure 2 : Code Conversion Chart.

INPUTS				INPUT CODES						OUTPUT NUMBER															
				Hexa Decimal		Decimal																			
D	C	B	A	4 BIT BINARY	4 BIT GRAY	EXCESS 3	EXCESS 3 GRAY	AIKEN	4221	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
0	0	0	0	0	0			0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	0	1	1	1			1	1	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	1	0	2	3		0	2	2	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	
0	0	1	1	3	2	0	3	3		0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	
0	1	0	0	4	7	1	4	4		0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	
0	1	0	1	5	6	2			3	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	
0	1	1	0	6	4	3	1		4	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	
0	1	1	1	7	5	4	2			0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	
1	0	0	0	8	15	5				0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	
1	0	0	1	9	14	6			5	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	
1	0	1	0	10	12	7	9		6	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	
1	0	1	1	11	13	8		5		0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	
1	1	0	0	12	8	9	5	6		0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	
1	1	0	1	13	9		6	7	7	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	
1	1	1	0	14	11		8	8	8	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0
1	1	1	1	15	10		7	9	9	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1

TYPICAL APPLICATIONS (continued)

Figure 3 : 6-bit binary to 1 of 64 Address Decoder.

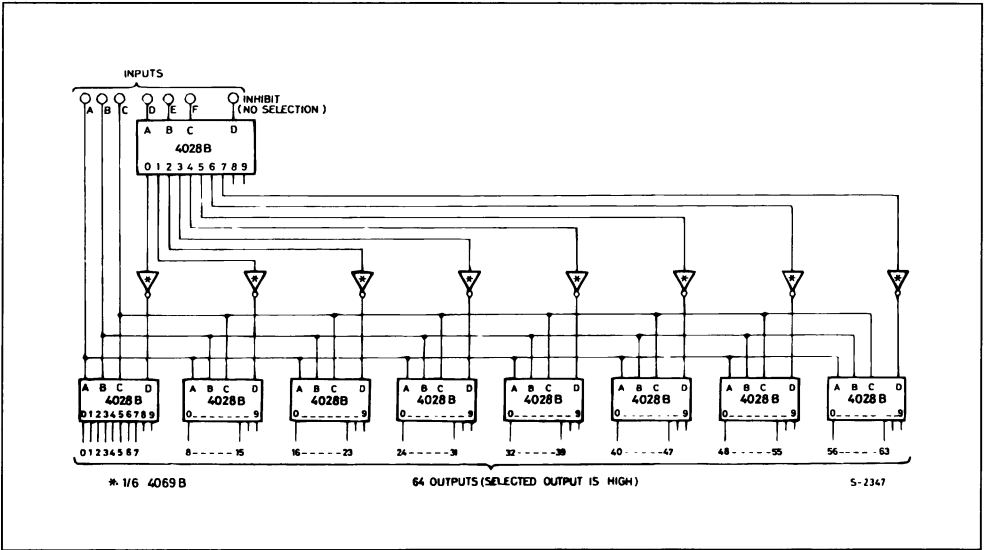
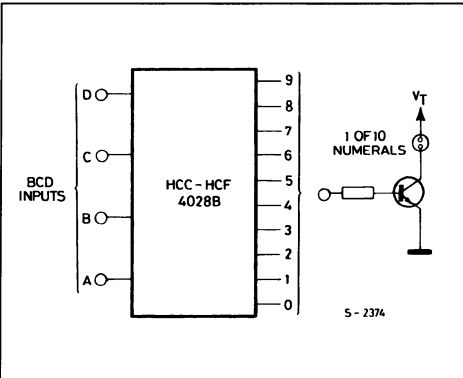
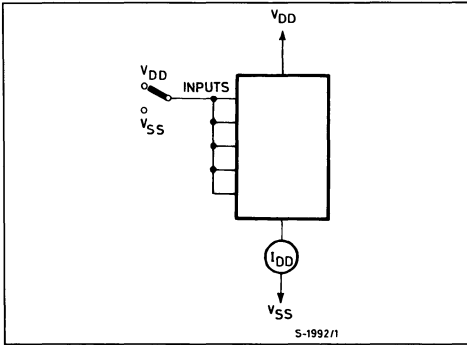


Figure 4 : Neon Readout (nixie tube) Display Application.

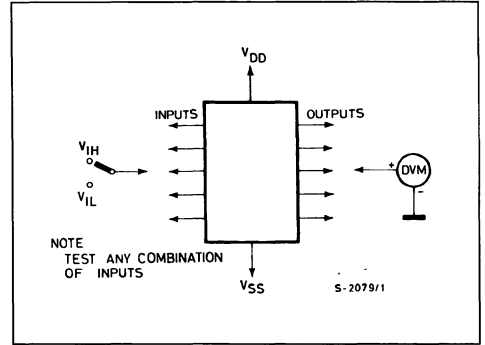


TEST CIRCUITS

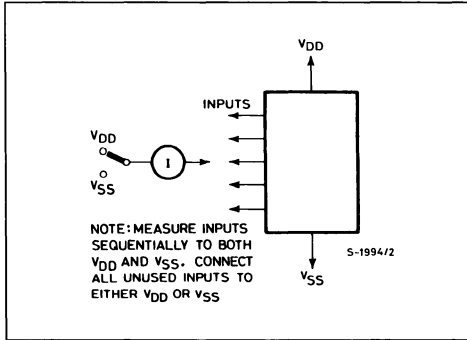
Quiescent Device Current.



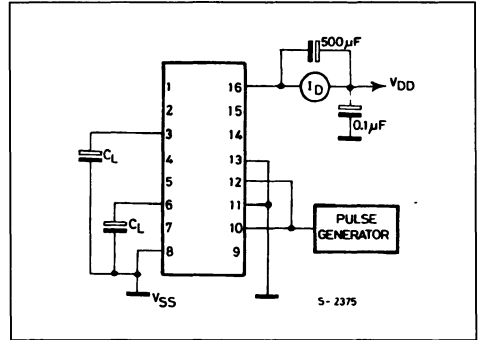
Noise Immunity.



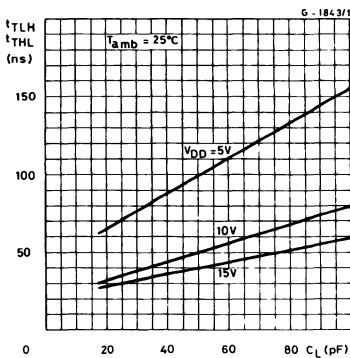
Input Leakage Current.



Dynamic Power Dissipation.

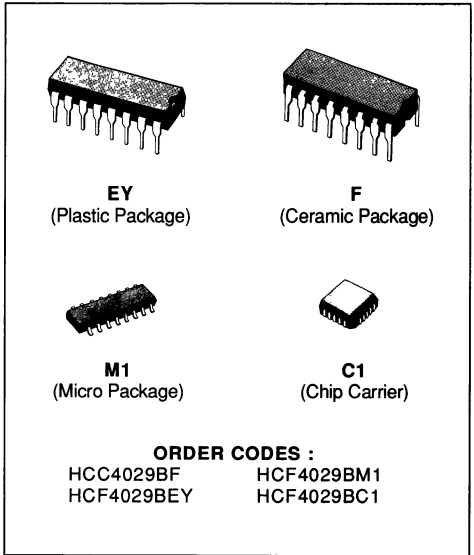


Typical Transition Time vs. Load Capacitance.



PRESETTABLE UP/DOWN COUNTER BINARY OR BCD DECADE

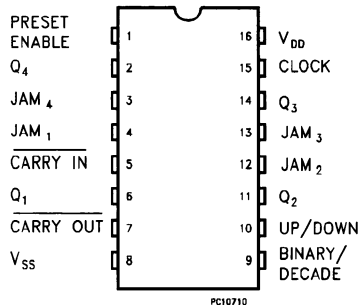
- MEDIUM SPEED OPERATION - 8MHz (typ.) @ $C_L = 50\text{pF}$ AND $V_{DD}-V_{SS} = 10\text{V}$
- MULTI-PACKAGE PARALLEL CLOCKING FOR SYNCHRONOUS HIGH SPEED OUTPUT RESPONSE OR RIPPLE CLOCKING FOR SLOW CLOCK INPUT RISE AND FALL TIMES
- "PRESET ENABLE" AND INDIVIDUAL "JAM" INPUTS PROVIDED
- BINARY OR DECADE UP/DOWN COUNTING
- BCD OUTPUTS IN DECADE MODE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC4029B** (extended temperature range) and **HCF4029B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4029B** consists of a four-stage binary or BCD-decade up/down counter with provisions for look-ahead carry in both counting modes. The inputs consist of a single CLOCK, CARRY-IN (CLOCK ENABLE), BINARY/DECADE, UP/DOWN, PRESET ENABLE, and four individual JAM signals. Q1, Q2, Q3, Q4 and a CARRY OUT signal are provided as outputs. A high PRESET ENABLE signal allows information on the JAM INPUTS to preset the counter to any state asynchronously with the clock. A low on each JAM line, when the PRESET-ENABLE signal is high, resets the counter to its zero count. The counter is advanced one count at the positive transition of the clock when the CARRY-IN and PRESET ENABLE signals, are low. Advancement is inhibited when the CARRY-IN or PRESET ENABLE signals are high. The CARRY-OUT signal is normally high and goes

PIN CONNECTIONS

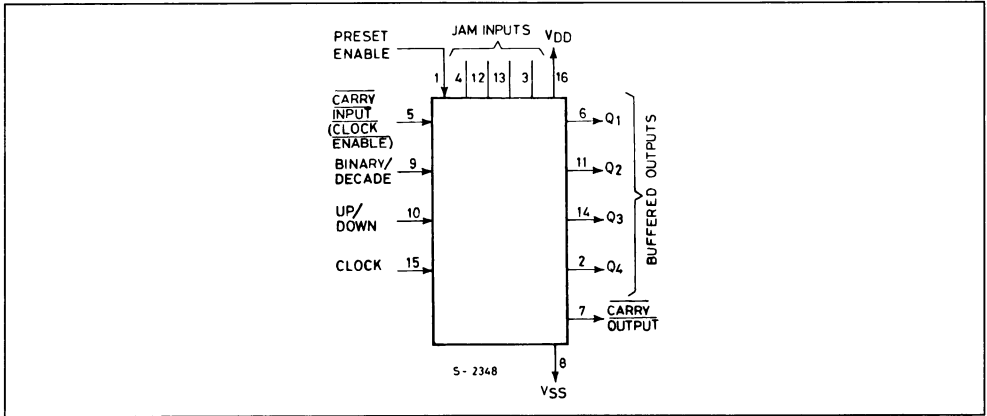


NC = No Internal Connection

counter reaches its maximum count in the UP mode or the minimum count in the DOWN mode provided the CARRY-IN signal is low. The CARRY-IN signal in the low state can thus be considered a CLOCK ENABLE. The CARRY-IN terminal must be connected to V_{SS} when not in use. Binary counting is accomplished when the BINARY/DECADE input is high ; the counter counts in the decade mode when the BINARY/DECADE input is low. The counter

counts Up when to UP/DOWN INPUT is high, and Down when the UP/DOWN INPUT is low. Multiple packages can be connected in either a parallel-clocking or a ripple-clocking arrangement as shown in cascading counter packages. Parallel clocking provides synchronous control and hence faster response from all counting outputs. Ripple-clocking allows for longer clock input rise and fall times.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage. HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C
T _{stg}	Storage Temperature	-65 to +150	°C

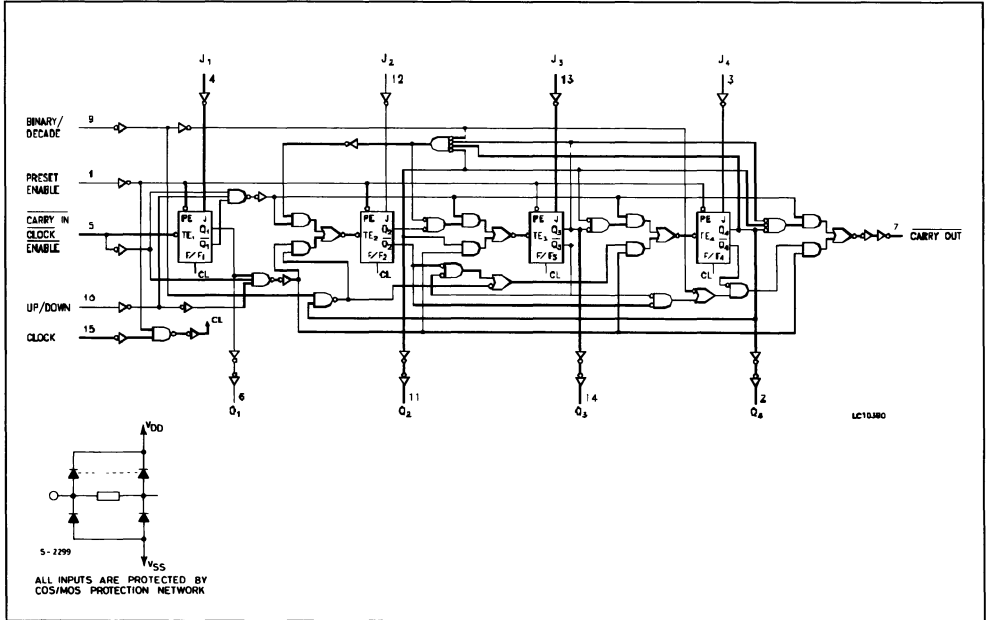
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

LOGIC DIAGRAMS



TRUTH TABLES

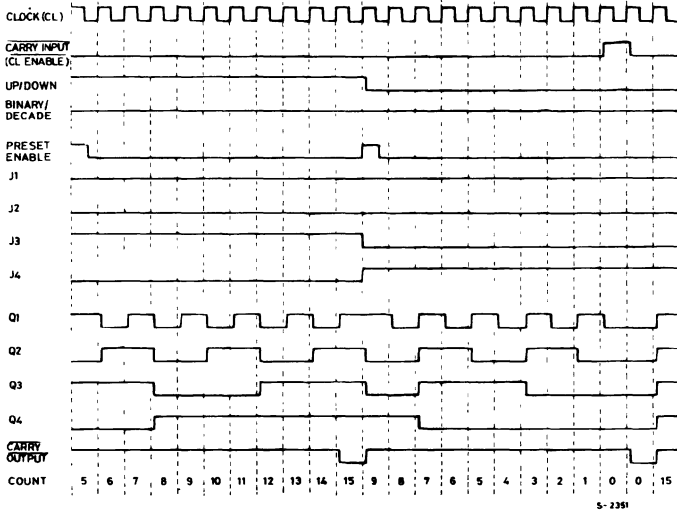
CLOCK	TE	PE	J	Q	\bar{Q}
X	X	0	0	0	1
\downarrow	0	1	X	\bar{Q}	Q
X	X	0	1	1	0
\downarrow	1	1	X	Q	\bar{Q} NC
\downarrow	X	1	X	Q	\bar{Q} NC

X DONT CARE

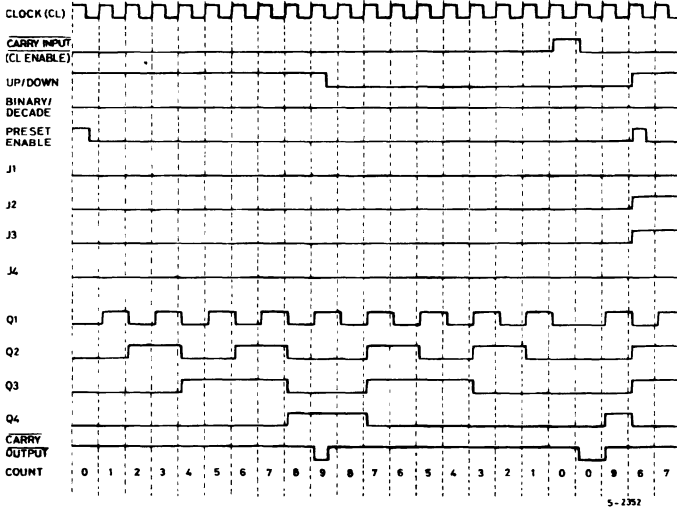
Control Input	Logic Level	Action
BIN/DEC (B/D)	1	Binary Count
	0	Decade Count
UP/DOWN (U/D)	1	Up Count
	0	Down Count
Preset Enable (PE)	1	Jam In
	0	No Jam
Carry In (CI) (Clock Enable)	1	No Counter Advance at Pos. Clock Transition
	0	Advance Counter at Pos. Clock Transition

TIMING DIAGRAMS

Binary Mode



Decade Mode



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95				4.95			
		0/10	< 1	10	9.95		9.95				9.95			
		0/15	< 1	15	14.95		14.95				14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05			0.05		
		10/0	< 1	10		0.05			0.05			0.05		
		15/0	< 1	15		0.05			0.05			0.05		
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5				3.5			
		1/9	< 1	10	7		7				7			
		1.5/13.5	< 1	15	11		11				11			
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5			1.5			1.5		
		9/1	< 1	10		3			3			3		
		13.5/1.5	< 1	15		4			4			4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
0/10	9.5			10	-1.3		-1.1	-2.6		-0.9				
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1		
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1		
C _I	Input Capacitance		Any Input					5	7.5			pF		

* T_{Low} = -55 °C for HCC device; -40 °C for HCF device.* T_{High} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

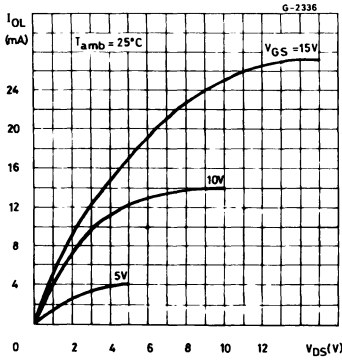
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time (Q Outputs)		5		250	500	ns
			10		120	240	
			15		90	180	
t_{PLH} t_{PHL}	Propagation Delay Time (Carry Output)		5		280	560	ns
			10		130	260	
			15		95	190	
t_{TLH} t_{THL}	Transition Time (Q Outputs, Carry Output)		5		100	200	ns
			10		50	100	
			15		40	80	
t_w	Minimum Clock Pulse Width		5		90	180	ns
			10		45	90	
			15		30	60	
t_r, t_f^{**}	Clock Rise and Fall Time		5			15	μs
			10			15	
			15			15	
t_{setup}^*	Minimum Setup Time (Carry Input)		5		30	60	ns
			10		10	20	
			15		6	12	
t_{setup}	Minimum Setup Time (B/D or UD)		5		170	340	ns
			10		70	140	
			15		50	100	
f_{max}	Maximum Clock Input Frequency		5	2	4		MHz
			10	4	8		
			15	5.5	11		
PRESET ENABLE							
t_{PLH} t_{PHL}	Propagation Delay Time (Q Outputs)		5		235	470	ns
			10		100	200	
			15		80	160	
t_{PLH} t_{PHL}	Propagation Delay Time (Carry Output)		5		320	640	ns
			10		145	290	
			15		105	210	
t_w	Minimum Preset Enable (Pulse Width)		5		65	130	ns
			10		35	70	
			15		25	50	
t_{rem}^*	Minimum Preset Enable (Removal Time)		5		100	200	ns
			10		55	110	
			15		40	80	
CARRY INPUT							
t_{PHL} t_{PLH}	Propagation Delay Time (Carry Output)		5		170	340	ns
			10		70	140	
			15		50	100	
t_{setup}^{***}	Minimum Setup Time (Carry In)		5		25	50	ns
			10		15	30	
			15		12	25	
t_{hold}	Minimum Hold Time (Carry In)		5		100	200	ns
			10		35	70	
			15		30	60	

* From Up/Down, Binary/Decade, Carry In or Preset Enable Control Inputs to Clock Edge

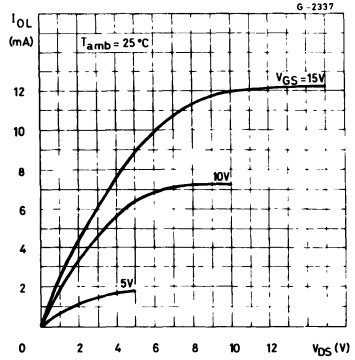
** If more than one unit is cascaded in the parallel clocked application it should be made less than or equal to the sum of the fixed propagation delay at 15 pF and the transition time of the carry output driving stage for the estimated capacitance load.

*** From Carry in to Clock Edge.

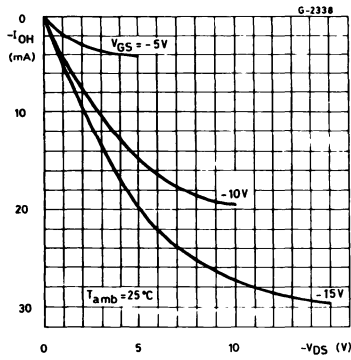
Typical Output Low (sink) Current Characteristics.



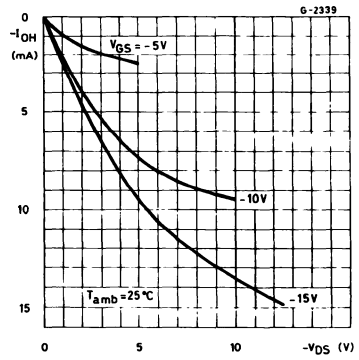
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

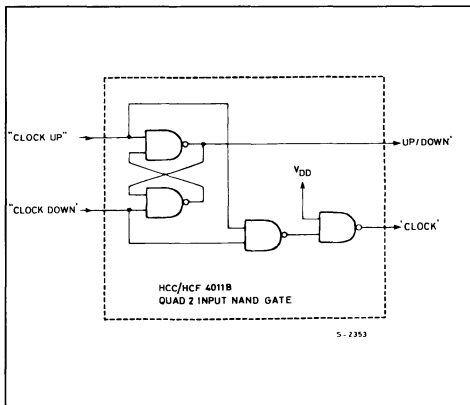


Minimum Output High (source) Current Characteristics.



APPLICATIONS

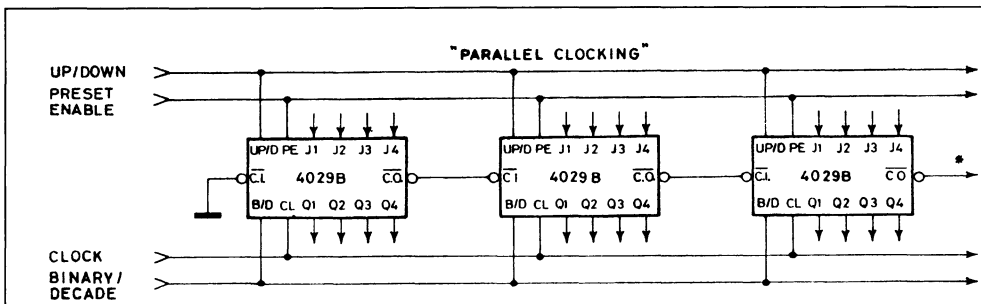
Conversion of Clock up, Clock Down Input Signals to Clock and Up/Down Inputs Signals.



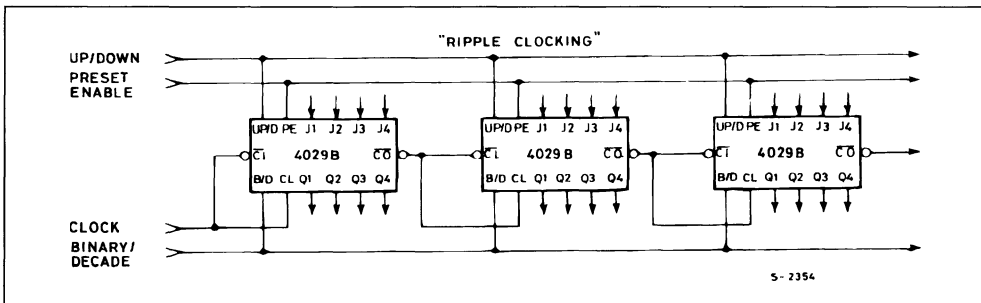
The **HCC/HCF4029B** CLOCK and UP/DOWN inputs are used directly in most applications. In applications where CLOCK UP and CLOCK DOWN inputs are provided, conversion to the **HCC/HCF4029B** CLOCK and UP/DOWN inputs can easily be realized by use of the circuit.

HCC/HCF4029B changes count on positive transitions of CLOCK UP or CLOCK DOWN inputs. For the gate configuration shown below, when counting up the CLOCK DOWN input must be maintained high and conversely when counting down the CLOCK UP input must be maintained high.

Cascading Counter Packages.



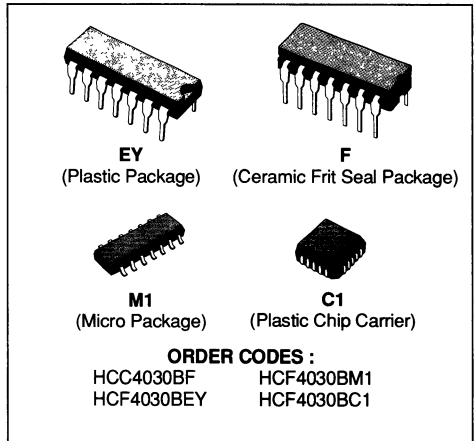
* CARRY-OUT lines at the 2nd, 3rd, et., stages may have a negative-going glitch pulse resulting from differential delays of different **HCC/HCF4029B** IC's. These negative-going glitches do not affect proper **HCC/HCF4029B** operation. However, if the CARRY-OUT signals are used to trigger other edge-sensitive logic devices, such as FF's or counters, the CARRY-OUT signals should be gated with the clock signal using a 2-input NOR gate such as **HCC/HCF4001B**



Ripple Clcking Mode : The Up/Down control can be changed at any count. The only restriction on changing the Up/Down control is that the clock input to the first counting stage must be high.

QUAD EXCLUSIVE-OR GATE

- MEDIUM-SPEED OPERATION – $t_{PHL} = t_{PLH} = 60\text{ns}$ (typ.) @ $C_L = 50\text{pF}$ and $V_{DD} - V_{SS} = 10\text{V}$
- LOW OUTPUT IMPEDANCE : 500Ω (typ.) @ $V_{DD} - V_{SS} = 10\text{V}$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

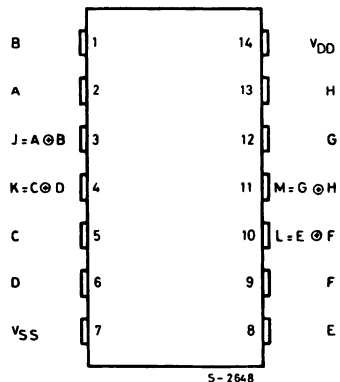


DESCRIPTION

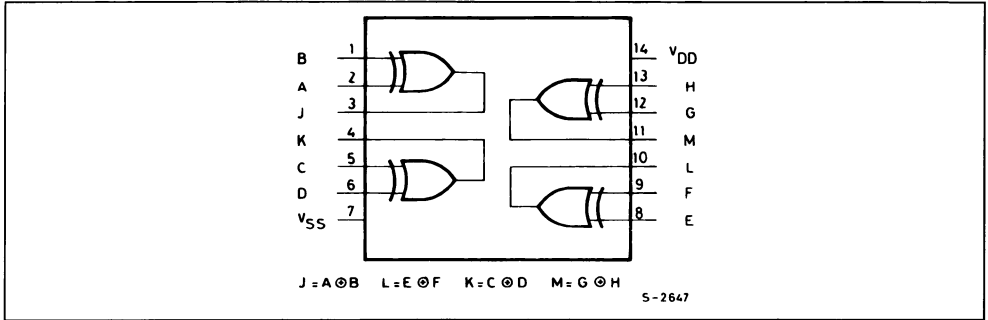
The **HCC4030B** (extended temperature range) and **HCF4030B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4030B** types consist of four independent exclusive-OR gates integrated on a single monolithic silicon chip. Each exclusive-OR gate consists of four n-channel and four p-channel enhancement-type transistors. All inputs and outputs are protected against electrostatic effects.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage: HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature: HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T_{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltages are referred to V_{SS} pin voltage.

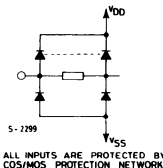
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

TRUTH TABLE

One of Four Identical Gates

A	B	J
0	0	0
1	0	1
0	1	1
1	0	0



Where "1" = High level
"0" = Low level.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

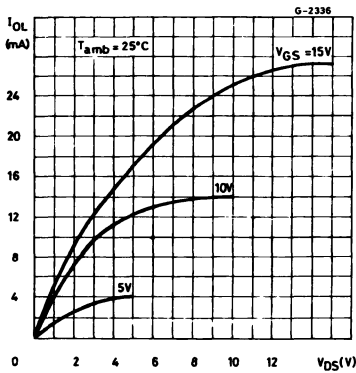
Symbol	Parameter		Test Conditions				Value						Unit		
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5		1	0.02	1		30	μ A		
			0/10			10		2	0.02	2		60			
			0/15			15		4	0.02	4		120			
			0/20			20		20	0.04	20		600			
		HCF Types	0/5			5		4	0.02	4		30			
			0/10			10		8	0.02	8		60			
			0/15			15		16	0.02	16		120			
V _{OH}		Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
	0/10			< 1	10	9.95		9.95			9.95				
	0/15			< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05	0.05	V			
		10/0		< 1	10		0.05			0.05	0.05				
		15/0		< 1	15		0.05			0.05	0.05				
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V			
			1/9	< 1	10	7		7			7				
			1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5	1.5	V			
			9/1	< 1	10		3			3	3				
			13.5/1.5	< 1	15		4			4	4				
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA		
			0/5	4.6		5	-0.64		-0.51	-1		-0.36			
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52		-0.44	-1		-0.36			
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
0/15		13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA		
			0/10	0.5		10	1.6		1.3	2.6		0.9			
			0/15	1.5		15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36			
			0/10	0.5		10	1.3		1.1	2.6		0.9			
			0/15	1.5		15	3.6		3.0	6.8		2.4			
		I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1			± 1
HCF Types				0/15	15										
C _I	Input Capacitance		Any Input						5	7.5		pF			

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is .1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

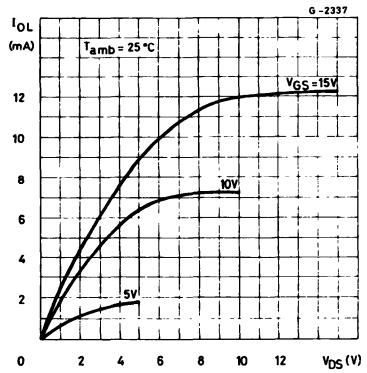
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{CC} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		140	280	ns
			10		65	130	
			15		50	100	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

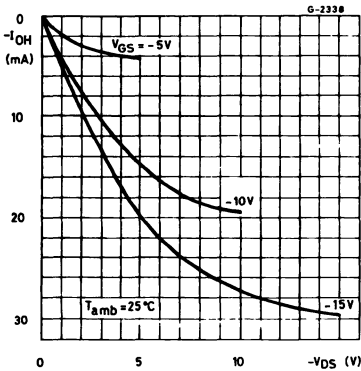
Typical Output Low (sink) Current Characteristics.



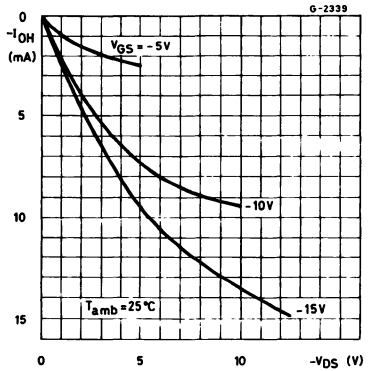
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

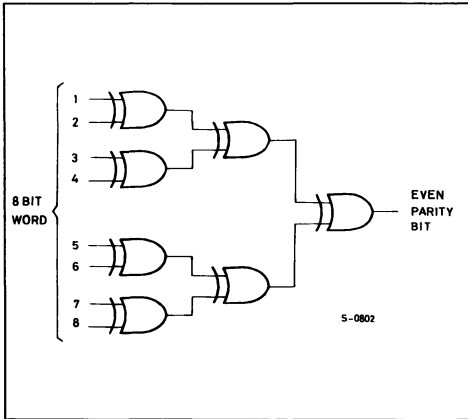


Minimum Output High (source) Current Characteristics.

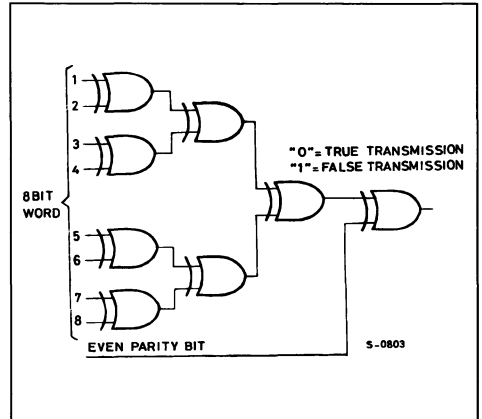


TYPICAL APPLICATIONS

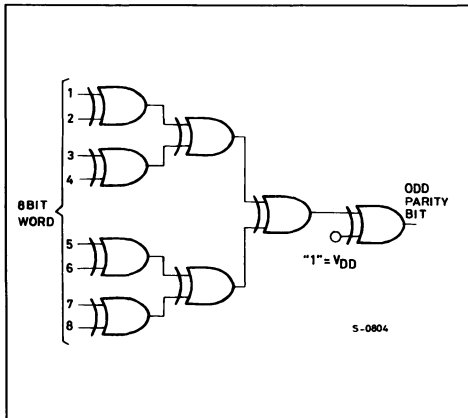
EVEN-PARITY-BIT GENERATOR
(1-3/4 x HCC/HCF4030B).



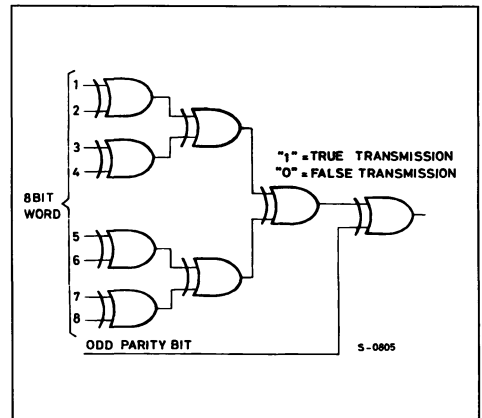
EVEN-PARITY-CHECKER
(2 x HCC/HCF4030B).



ODD-PARITY-BIT GENERATOR
(2 x HCC/HCF4030B).

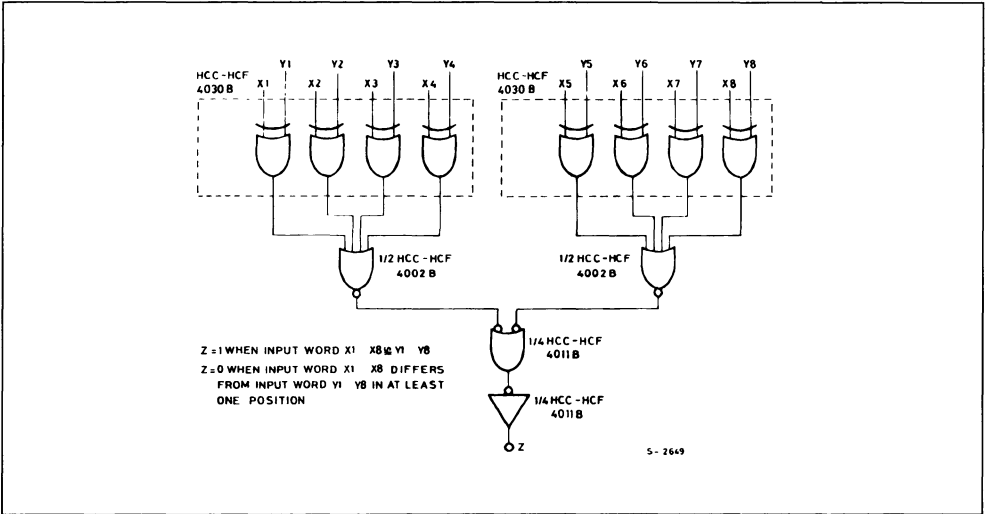


ODD-PARITY CHECKER
(2 x HCC/HCF4030B).



TYPICAL APPLICATIONS (continued)

8-BIT COMPARATOR



8-BIT TWO'S COMPLEMENT ADDER-SUBTRACTOR

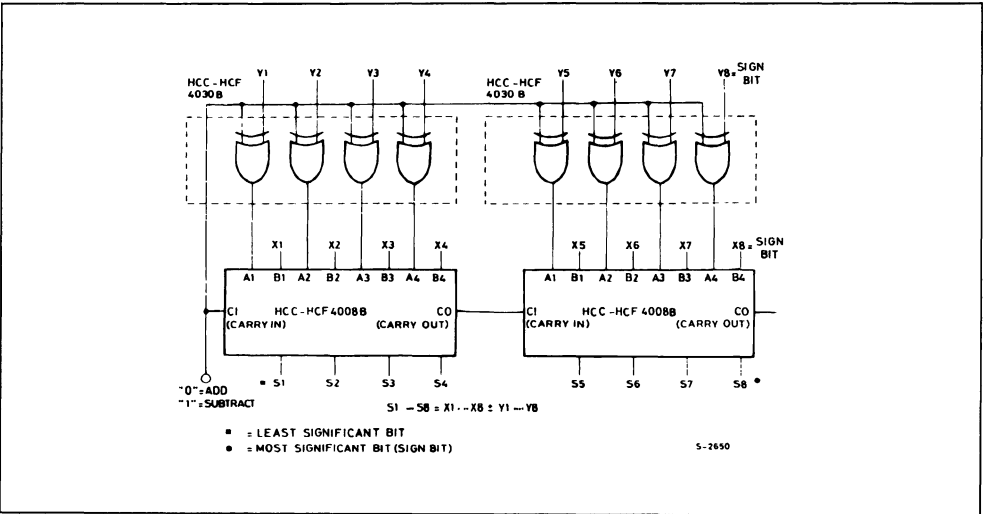


Table 1 : Two's Complement Numbers and Their Equivalent Decimal Values.

X ₈	X ₇	X ₆	X ₅	X ₄	X ₃	X ₂	X ₁			X ₈	X ₇	X ₆	X ₅	X ₄	X ₃	X ₂	X ₁			
0	0	0	0	0	0	0	0	=	0	1	1	1	1	1	1	1	1	1	=	-1
0	0	0	0	0	0	0	1	=	1	1	1	1	1	1	1	1	0	=	-2	
0	0	0	0	0	0	1	0	=	2	1	1	1	1	1	1	0	1	=	-3	
0	0	0	0	0	0	1	1	=	3	1	1	1	1	1	1	0	0	=	-4	
										1	1	1	1	1	0	1	1	=	-5	
0	1	1	1	1	1	1	0	=	126	1	0	0	0	0	0	0	1	=	-127	
0	1	1	1	1	1	1	1	=	127	1	0	0	0	0	0	0	0	=	-128	

The two's complement adder-subtractor can add or subtract any two of the numbers in table 1. For example :

a) 2 SIGN BIT
 + = BIT
 -5 X 0 0 0 0 0 0 1 0 2 +
 Y 1 1 1 1 1 0 1 1 -5 +
 CI 0

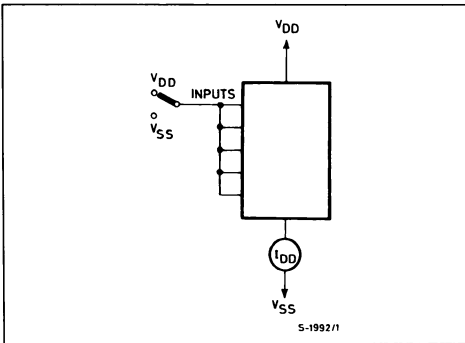
 S 0 1 | 1 1 1 1 1 0 1 = -3
 CO

b) -2 SIGN BIT
 - = X BIT
 -5 Y 1 1 1 1 1 1 1 0 -2 +
 Y 0 1 1 1 1 0 1 1 -5
 CL 1

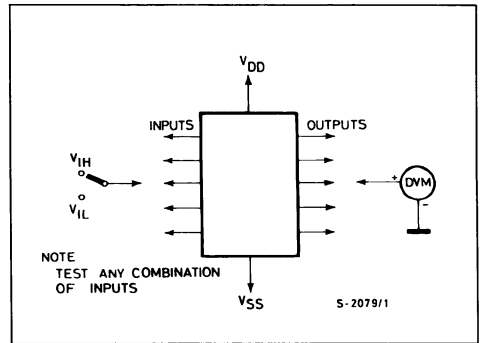
 S 1 0 | 0 0 0 0 0 1 1 = 3
 CO

TEST CIRCUITS

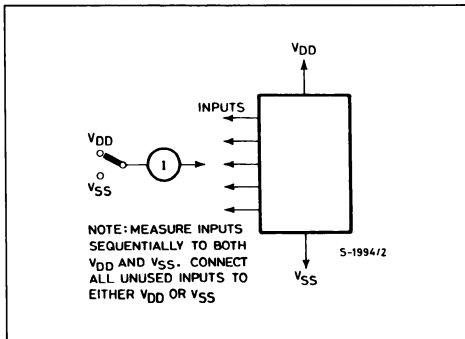
Quiescent Device Current.



Input Voltage.

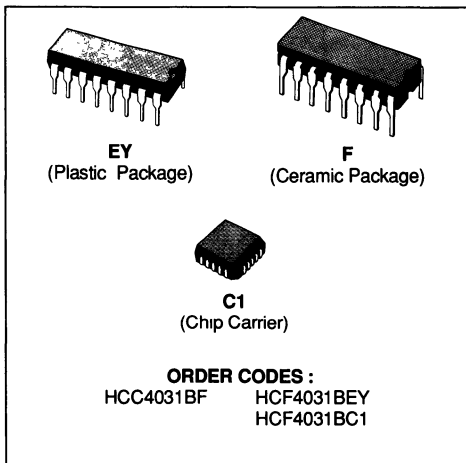


Input Leakage Current.



64-STAGE STATIC SHIFT REGISTER

- FULLY STATIC OPERATION : DC to 16MHz (TYP.) @ $V_{DD} - V_{SS} = 15V$
- STANDARD TTL DRIVE CAPABILITY ON Q OUTPUT
- RECIRCULATION CAPABILITY
- THREE CASCADING MODES :
 DIRECT CLOCKING FOR HIGH-SPEED OPERATION
 DELAYED CLOCKING FOR REDUCED CLOCK DRIVE REQUIREMENTS
 ADDITIONAL 1/2 STAGE FOR SLOW CLOCKS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA at 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

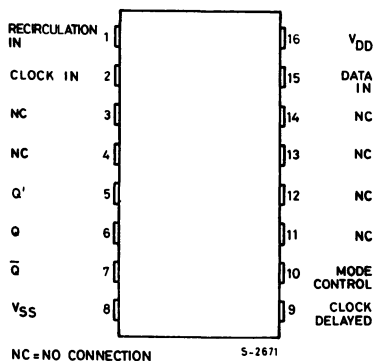


DESCRIPTION

The **HCC4031B** (extended temperature range) and **HCF4031B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package.

The **HCC/HCF4031B** is a static shift register that contains 64 D-type, master-slave flip-flop stages and one stage which is a D-type master flip-flop only (referred to as a 1/2 stage). The logic level present at the DATA input is transferred into the first stage and shifted one stage at each positive-going clock transition. Maximum clock frequencies up to 16 Megahertz (typical) can be obtained. Because fully static operation is allowed, information can be permanently stored with the clock line in either the low or high state. The **HCC/HCF4031B** has a MODE CONTROL input that, when in the high state, allows operation in the recirculating mode. The MODE CONTROL input can also be used to select between two separate data sources. Register packages can be cascaded and the clock lines driven directly for high-speed operation. Alternatively, a delayed clock output (CL_D) is provided that enables cascading

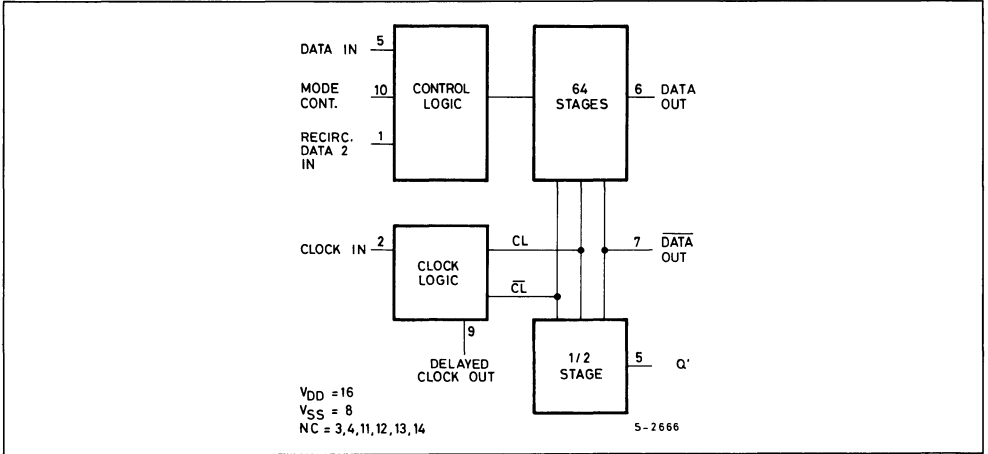
PIN CONNECTIONS



register packages while allowing reduced clock drive fan-out and transition-time requirements. A third cascading option makes use of the Q' output from the 1/2 stage, which is available on the next

negative-going transition of the clock after the Q output occurs. This delayed output, like the delayed clock CL_D, is used with clocks having slow rise and fall times.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

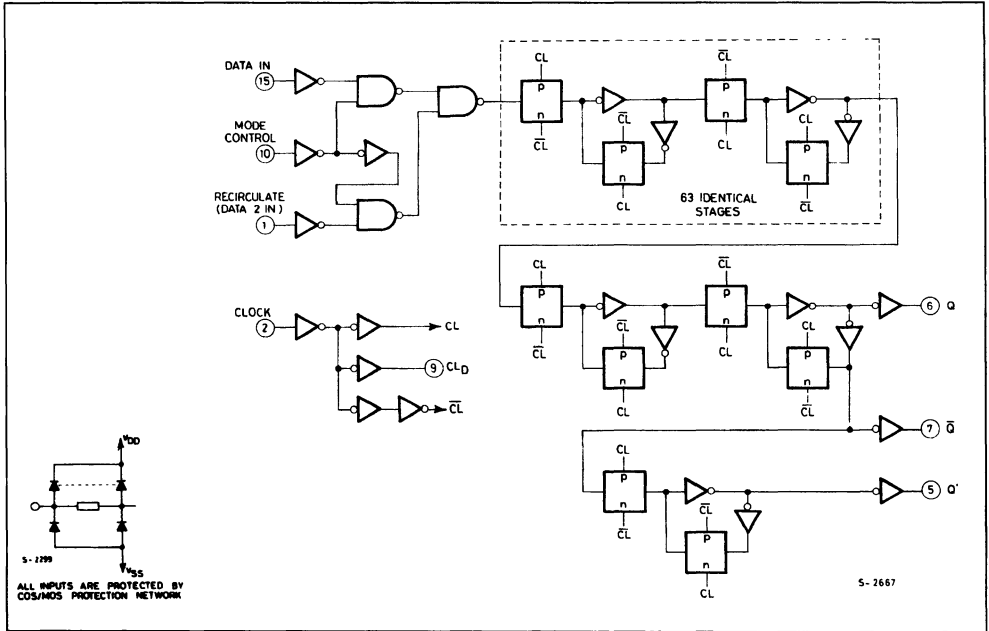
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to + 18 3 to + 15	V V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

LOGIC DIAGRAM AND TRUTH TABLES



INPUT CONTROL CIRCUIT

Data	Recirc.	Mode	Bit Into Stage 1
1	X	0	1
0	X	0	0
X	1	1	1
X	0	1	0

TYPICAL STAGE

Data	CL	Data + 1
0		0
1		1
X		NC

1 = HIGH LEVEL

0 = LOW LEVEL
X = DON'T CARE

OUTPUT FROM Q' (pin 5)

Data + 64	CL	Data + 64.5
0		0
1		1
X		NC

NC = NO CHANGE

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5			5	0.04	5	150	μ A	
			0/10			10			10	0.04	10	300		
			0/15			15			20	0.04	20	600		
			0/20			20			100	0.08	100	3000		
		HCF Types	0/ 5			5			20	0.04	20	150		
			0/10			10			40	0.04	40	300		
		0/15			15			80	0.04	80	600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95	V		
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		V		
		10/0		< 1	10		0.05			0.05	0.05			
		15/0		< 1	15		0.05			0.05	0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		V		
			9/1	< 1	10		3			3	3			
			13.5/1.5	< 1	15		4			4	4			
I _{OH}	Output Source Current (Source) Q, Q', Q CL _D	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
		0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4			
I _{OL}	Output Sink Current Q	HCC Types	0/ 5	0.4		5	2.56		2.04	4		1.44	mA	
			0/10	0.5		10	6.4		5.2	10.4		3.6		
			0/15	1.5		15	16.8		13.6	27.2		9.6		
		HCF Types	0/ 5	0.4		5	2.08		1.74	4		1.43		
			0/10	0.5		10	5.01		4.42	10.4		3.74		
			0/15	1.5		15	13.6		11.56	27.2		9.52		
I _{OL}	Output Sink Current Q, Q' CL _D	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	
		HCF Types	0/15											15
C _I	Input Capacitance			Any Input					5	7.5		pF		

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device

** T_{High} = + 125°C for HCC device ; + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH} , t_{PLH}	Propagation Delay Time : Clock to Q, Clock to Q		5		250	500	ns
			10		110	220	
			15		90	180	
t_{PHL} , t_{PLH} , t_{PHL}	Propagation Delay Time : Clock to Q' Clock to Q		5		190	380	ns
			10		80	160	
			15		65	130	
	Clock to CL_D		5		100	200	ns
			10		50	100	
			15		40	80	
t_{THL} , t_{TLH}	Transition Time : (any output, except $Q_{t_{THL}}$)		5		100	200	ns
			10		50	100	
			15		40	80	
t_{THL}	Q,		5		50	100	ns
			10		25	50	
			15		20	40	
t_{setup}	Data Setup Time		5		30	60	ns
			10		15	30	
			15		10	20	
t_{hold}	Data Hold Time		5		30	60	ns
			10		15	30	
			15		10	20	
t_w	Clock Pulse Width		5		120	240	ns
			10		50	100	
			15		40	80	
f_{max}	Maximum Clock Input Frequency**		5	2	4		MHz
			10	5	10		
			15	6	12		
t_r , t_f	Clock Input Rise or Fall Time*		5			1000	μs
			10			1000	
			15			200	

* If more than one unit is cascaded in the parallel clocked application, t_{rCL} should be made less than or equal to the sum of the propagation delay at 50pF and the transition time of the output driving stage.

** Maximum Clock Frequency for Cascaded Units;

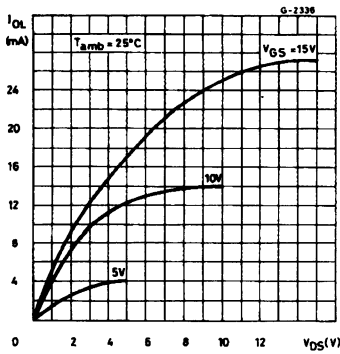
a) Using Delayed Clock Feature in Recirculation Mode

$$f_{max} = \frac{1}{(n-1) \text{ CLD prop delay} + Q \text{ prop delay} + \text{set-up time}} \quad \text{where } n = \text{number of packages}$$

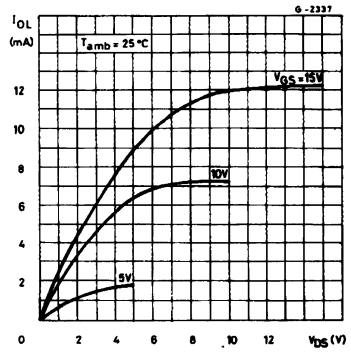
b) Not Using Delayed Clock :

$$f_{max} = \frac{1}{\text{propagation delay} + \text{set-up time}}$$

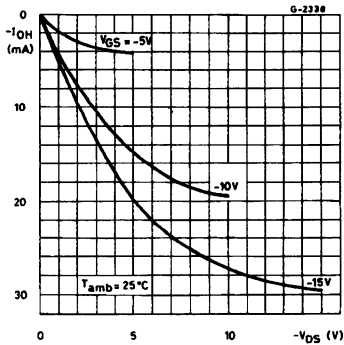
Typical Output Low (sink) Current Characteristics.



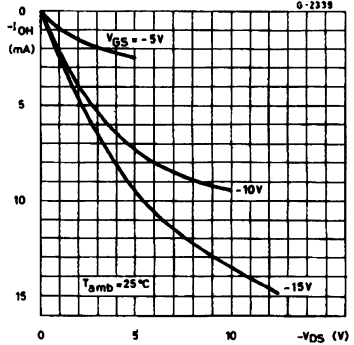
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

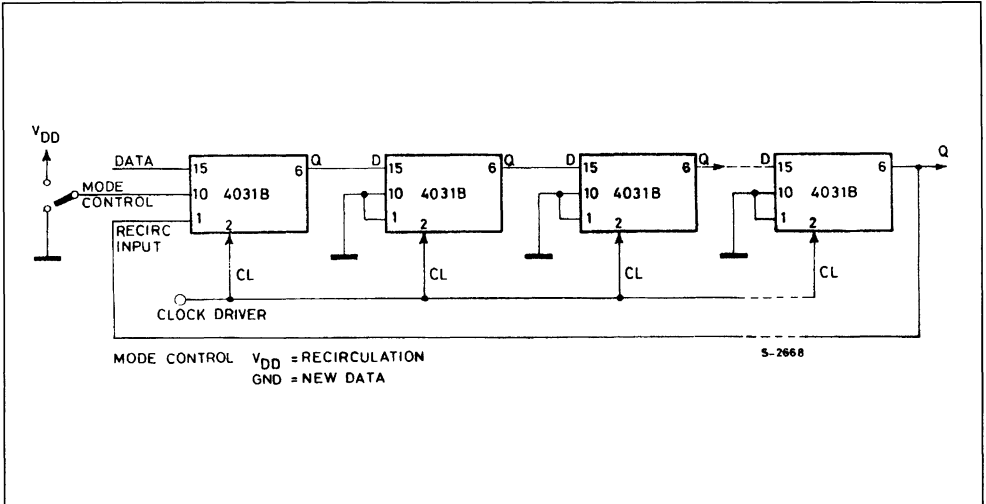


Minimum Output High (source) Current Characteristics.

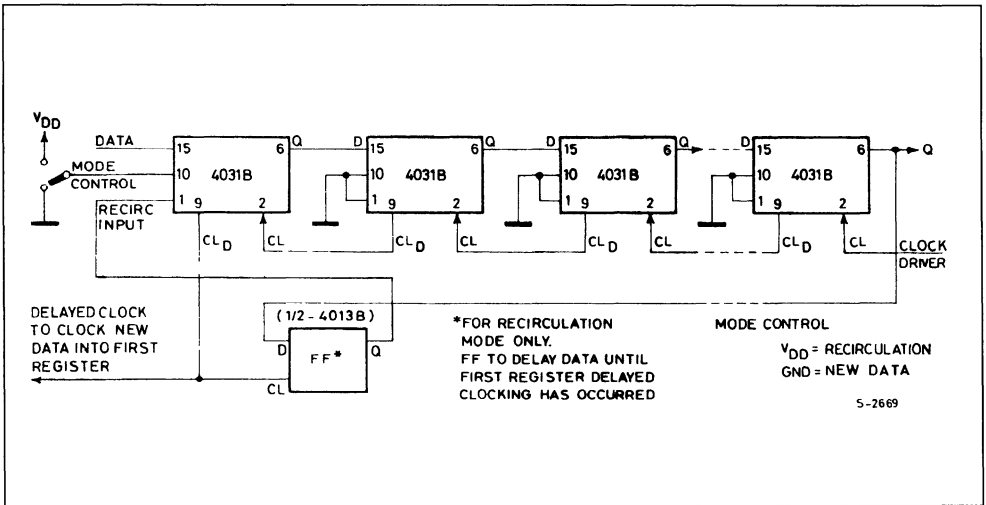


TYPICAL APPLICATIONS

CASCADING USING DIRECT CLOCKING FOR HIGH SPEED OPERATION (SEE CLOCK RISE AND FALL TIME REQUIREMENT).

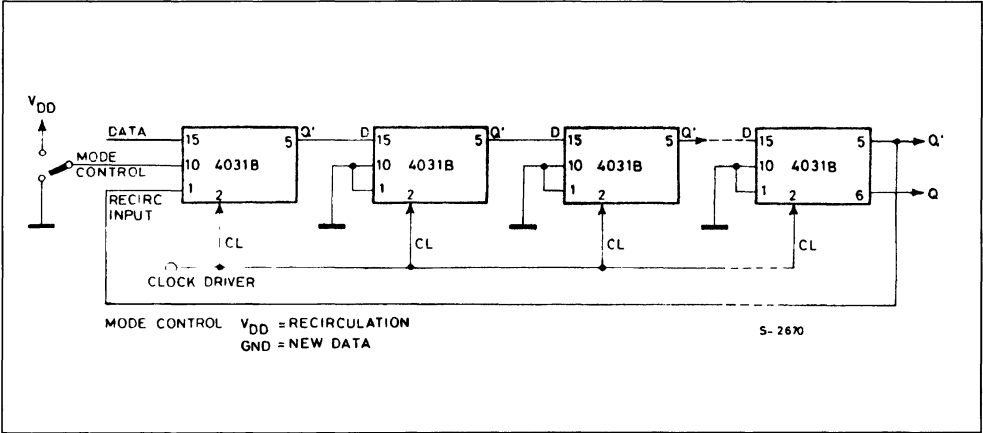


CASCADING USING DELAYED CLOCKING FOR REDUCED CLOCK DRIVE REQUIREMENTS.



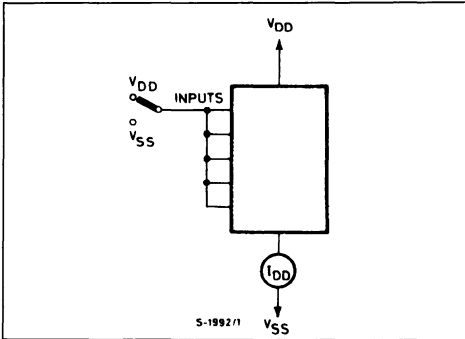
TYPICAL APPLICATIONS (continued)

CASCADING USING HALF- CLOCK-PULSE DELAYED DATA OUTPUT (Q') TO PERMIT USE OF SLOW RISE AND FALL TIME CLOCK INPUTS.

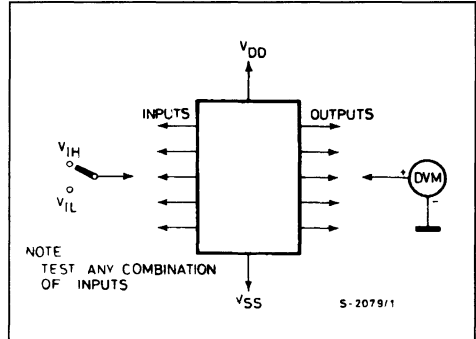


TEST CIRCUITS

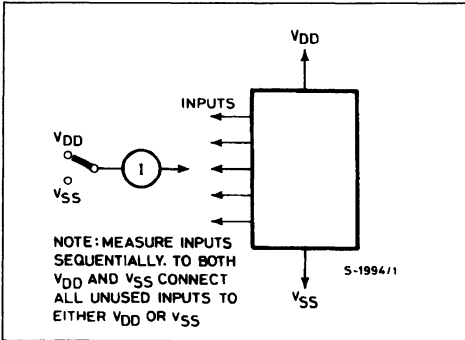
Quiescent Device Current.



Noise Immunity.

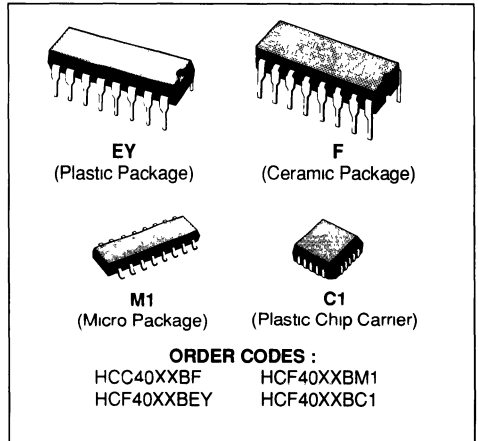


Input Leakage Current.



TRIPLE SERIAL ADDERS

- INVERT INPUTS ON ALL ADDERS FOR SUM COMPLEMENTING APPLICATIONS
- FULLY STATIC OPERATION...DC TO 10MHz (typ.) @ $V_{DD} = 10V$
- BUFFERED INPUTS AND OUTPUTS
- SINGLE-PHASE CLOCKING
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

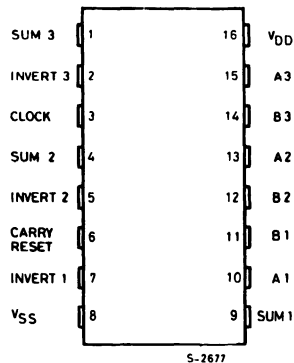


DESCRIPTION

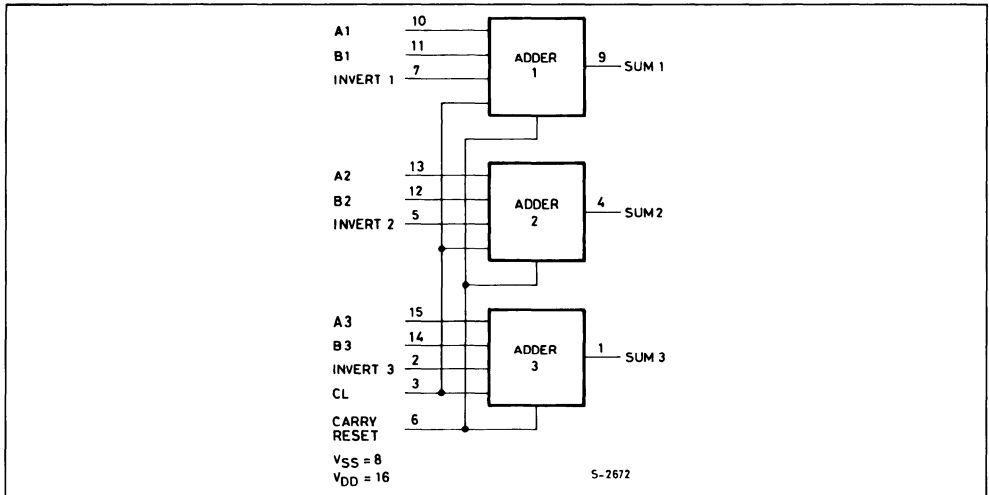
The **HCC/4032B/4038B** (extended temperature range) and **HCF4032B/4038B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4032B** and **HCC/HCF4038B** types consist of three serial adder circuits with common CLOCK and CARRY-RESET inputs. Each adder has two provisions for two serial DATA INPUT signals and an INVERT command signal. When the command signal is a logical "1", the sum is complemented. Data words enter the adder with the least significant bit first ; the sign bit trails. The output is the MOD 2 sum of the input bits plus the carry from the previous bit position. The carry is only added at the positive-going clock transition for the **HCC/HCF4032B** or at the negative-going clock for the **HCC/HCF4038B**, thus, for spike-free operation the input data transitions should occur as soon as possible after the triggering edge. The CARRY is reset to a logical "0" at the end of each word by applying a logical "1" signal to a CARRY-RESET input one-bit-position before the application of the first bit of the next word.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

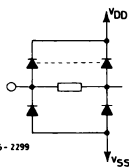
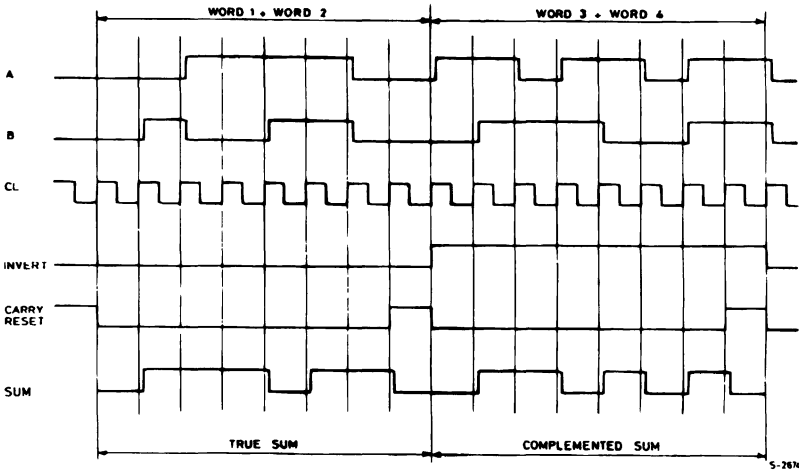
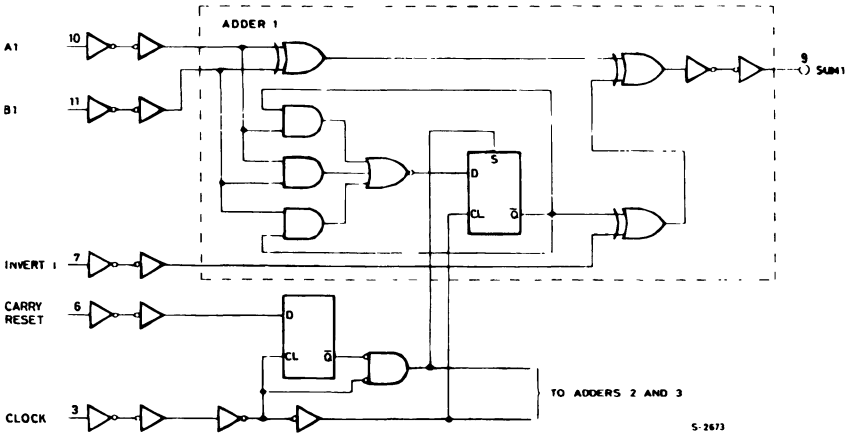
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC AND TIMING DIAGRAMS
(one of three serial adders)

4032B



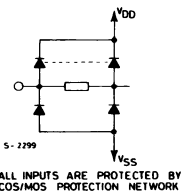
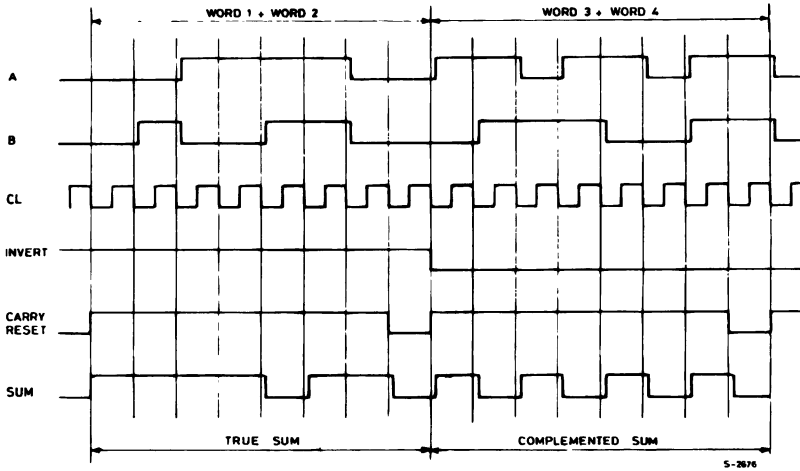
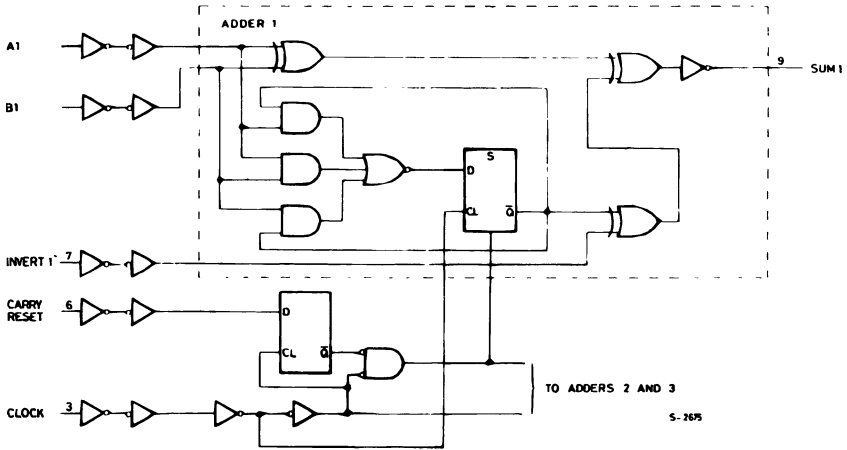
ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

WORD 1	0.0111100 = + 60	WORD 3	1.1011011 = - 37
WORD 2	0.0110010 = + 50	WORD 4	1.1001110 = - 50
	<u>0.1101110 = + 110</u>		<u>1.0101001 = - 87</u>

WORD 3	1.1011011 = - 37
WORD 4	1.1001110 = - 50
	<u>1.0101001 = - 87</u>

LOGIC AND TIMING DIAGRAMS (continued)

4038B



WORD 1	1.100011 = -61
WORD 2	1.1001101 = -51
	1.0010000 = -112

WORD 3	0.0100100 = +36
WORD 4	0.0110001 = +49
	0.1010101 = +85

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit		
			V _I (V)	V _O (V)	I _{OL} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A	
			0/10			10		10		0.04	10		300		
			0/15			15		20		0.04	20		600		
			0/20			20		100		0.08	100		3000		
		HCF Types	0/ 5			5		20		0.04	20		150		
			0/10			10		40		0.04	40		300		
			0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95			V	
		0/10		< 1	10	9.95		9.95			9.95				
		0/15		< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V		
		10/0		< 1	10		0.05			0.05		0.05			
		15/0		< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V		
			1/9	< 1	10	7		7			7				
			1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V		
			9/1	< 1	10		3			3		3			
			13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		-	1.15	mA	
			0/ 5	4.6		5	-	0.64		-	- 1		-		0.36
			0/10	9.5		10	- 1.6		- 1.3	- 2.6			- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8			- 2.4		
		HCF Types	0/ 5	2.5		5	-	1.53		-	- 3.2		-		1.1
			0/ 5	4.6		5	-	0.52		-	- 1		-		0.36
			0/10	9.5		10	- 1.3		- 1.1	- 2.6			- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8			- 2.4		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA		
			0/10	0.5		10	1.6		1.3	2.6		0.9			
			0/15	1.5		15	4.2		3.4	6.8		2.4			
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36			
			0/10	0.5		10	1.3		1.1	2.6		0.9			
			0/15	1.5		15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input			\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A		
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3			\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF		

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

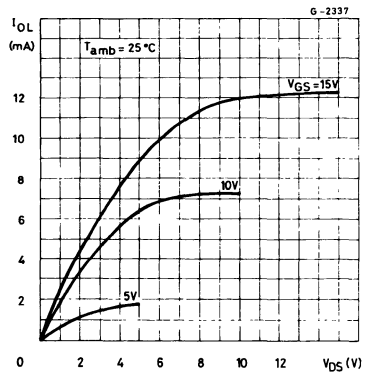
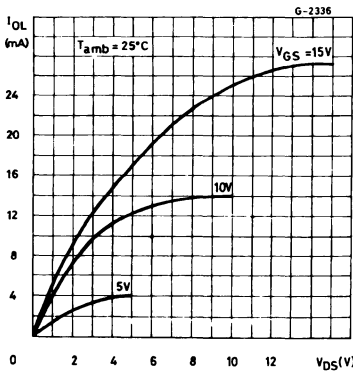
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_L = 50pF$, $R_L = 200k\Omega$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time A, B, or Inverter Inputs to Sum Outputs		5		260	520	ns
			10		120	240	
			15		90	180	
t_{PHL} , t_{PLH}	Propagation Delay Time (clock input to sum outputs)		5		325	650	ns
			10		175	350	
			15		150	300	
t_{THL} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{hold}	Data Input Hold Time (clock edge to A, B, or reset inputs)		5		120	200	ns
			10		50	80	
			15		40	60	
f_{max}	Maximum Clock Input Frequency		5	2.5	4.5		MHz
			10	5	10		
			15	7.5	15		
t_r , t_f^*	Clock Input Rise or Fall Time		5			500	μs
			10			500	
			15			500	

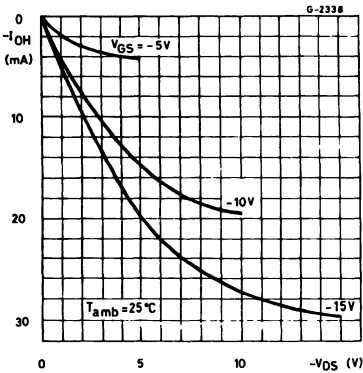
* If more than one unit is cascaded t_r should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving state for the estimated capacitive load

Typical Output Low (sink) Current.

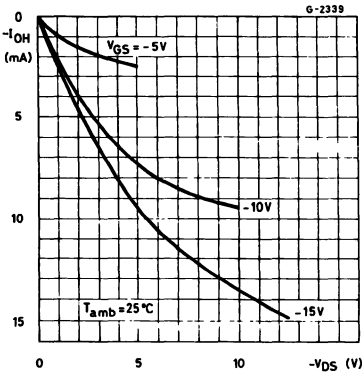
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

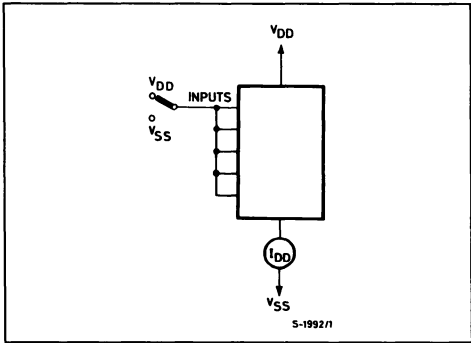


Minimum Output High (source) Current Characteristics.

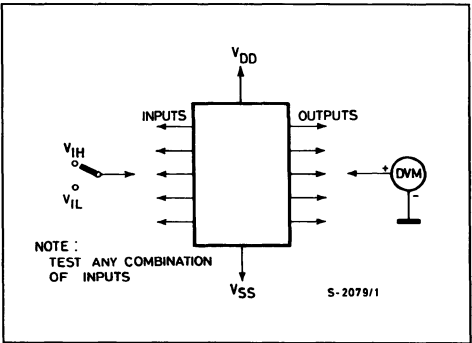


TEST CIRCUITS

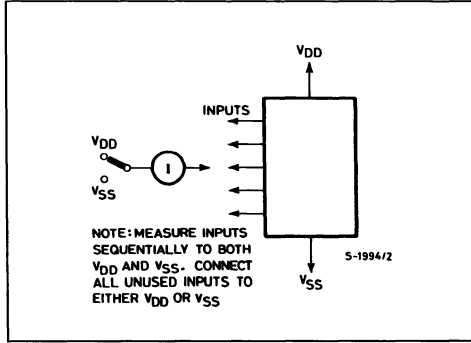
Quiescent Device Current.



Input Voltage.

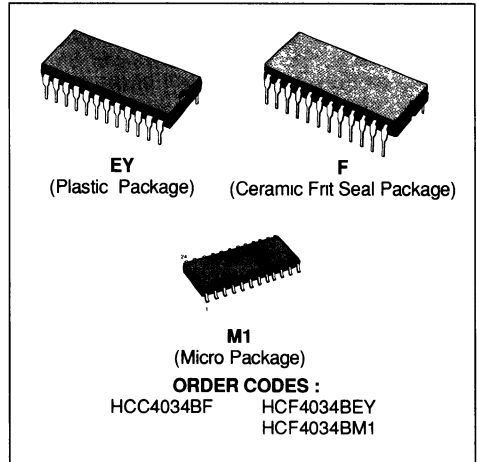


Input Current.



8-STAGE STATIC BIDIRECTIONAL PARALLEL/SERIAL INPUT/OUTPUT BUS REGISTER

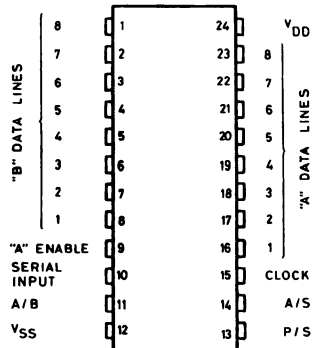
- BIDIRECTIONAL PARALLEL DATA INPUT
- PARALLEL OR SERIAL INPUTS/PARALLEL OUTPUTS
- ASYNCHRONOUS OR SYNCHRONOUS PARALLEL DATA LOADING
- PARALLEL DATA-INPUT ENABLE ON "A" DATA LINES (3-state output)
- DATA RECIRCULATION FOR REGISTER EXPANSION
- MULTIPACKAGE REGISTER EXPANSION
- FULLY STATIC OPERATIONAL DC-TO-5MHz (typ.) AT $V_{DD} = 10V$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC4034B** (extended temperature range) and **HCF4034B** (intermediate temperature range) are monolithic integrated circuits, available in 24-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4034B** is a static eight-stage parallel-or serial-input parallel-output register. It can be used to : 1) bidirectionally transfer parallel information between two buses ; 2) convert serial data to parallel form and direct the parallel data to either of two buses ; 3) store (recirculate) parallel data, or 4) accept parallel data from either of two buses and convert that data to serial form. Inputs that control the operations include a single-phase **CLOCK (CL)**, **A DATA ENABLE (AE)**, **ASYNCHRONOUS/SYNCHRONOUS (A/S)**, **A-BUS-TO-B-BUS/B-BUS-TO-A-BUS (A/B)**, and **PARALLEL/ SERIAL (P/S)**. Data inputs include 16 bidirectional parallel data lines of which the eight A data lines are inputs (3-state outputs) and the B data lines are outputs (inputs) depending on the signal level on the A/B input. In addition, an input for **SERIAL DATA** is also provided. All register stages are D-type master-slave flip-flops with separate

PIN CONNECTIONS



S-1461

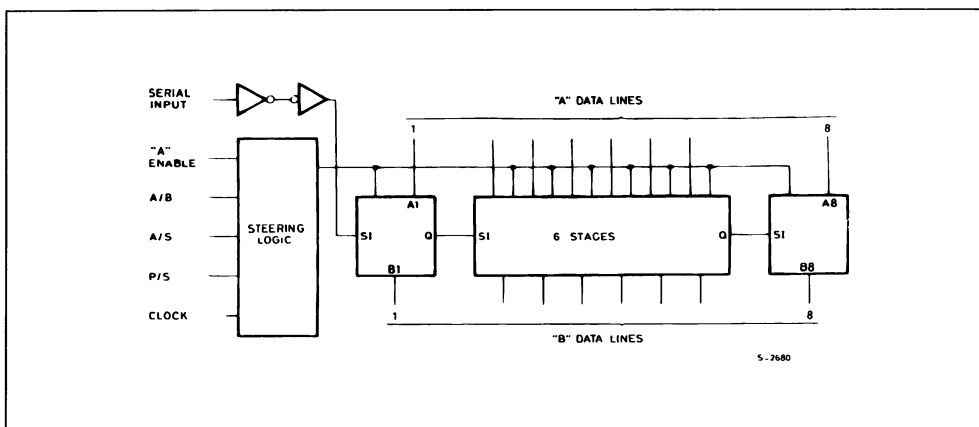
master and slave clock inputs generated internally to allow synchronous or asynchronous data transfer from master to slave. Isolation from external noise and the effects of loading is provided by output buffering.

PARALLEL OPERATION – A high P/S input signal allows data transfer into the register via the parallel data lines synchronously with the positive transition of the clock provided the A/S input is low. If the A/S input is high the transfer is independent of the clock. The direction of data flow is controlled by the A/B input. When this signal is high the A data lines are inputs (and B data lines are outputs); a low A/B signal reverses the direction of data flow. The AE-input is an additional feature which allows many registers

to feed data to a common bus. The A DATA lines are enabled only when this signal is high. Data storage through recirculation of data in each register stage is accomplished by making the A/B signal high and the AE signal low.

SERIAL OPERATION – A low P/S signal allows serial data to transfer into the register synchronously with the positive transition of the clock. The A/S input is internally disabled when the register is in the serial mode (asynchronous serial operation is not allowed). The serial data appears as output data on either the B lines (when A/B is high) or the A lines (when A/B is low and the AE signal is high). Register expansion can be accomplished by simply cascading HCC/HCF4034B packages.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

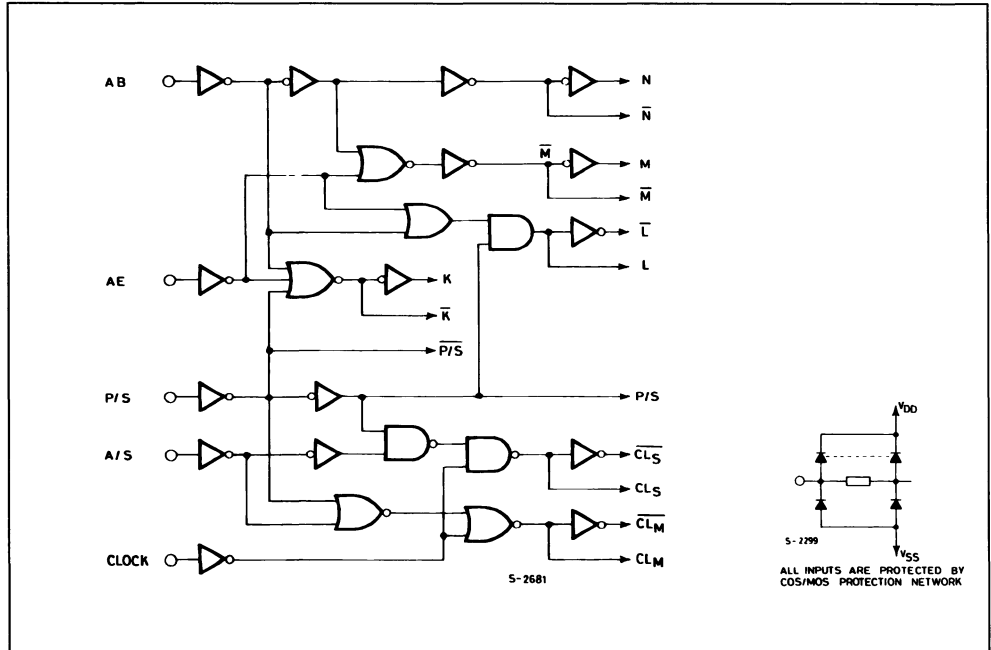
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

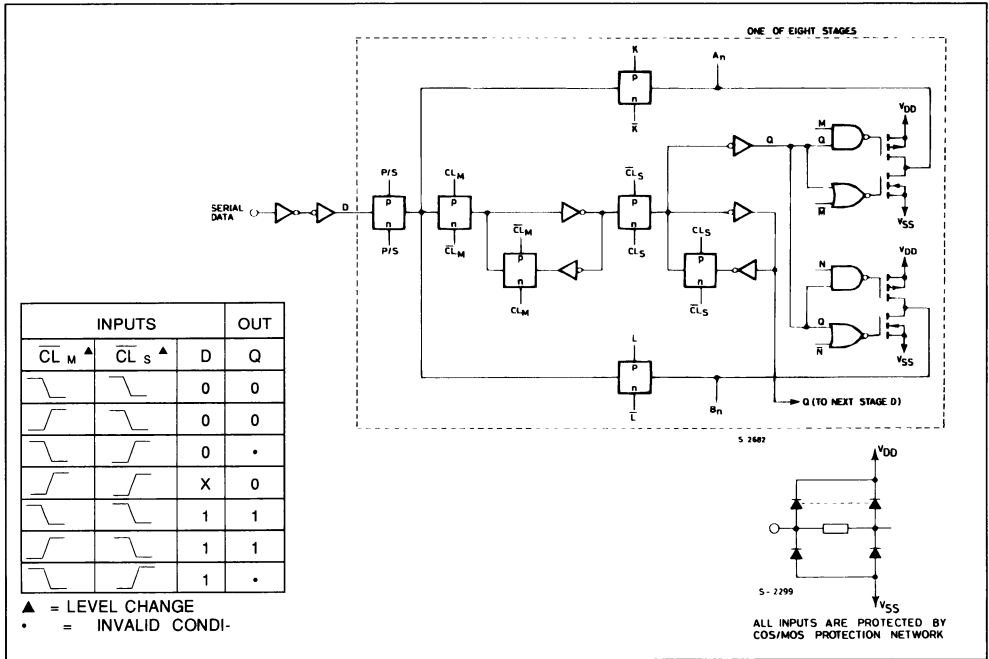
LOGIC DIAGRAMS

STEERING LOGIC



LOGIC DIAGRAM AND TRUTH TABLE

REGISTER STAGE (1 of 8 stages)

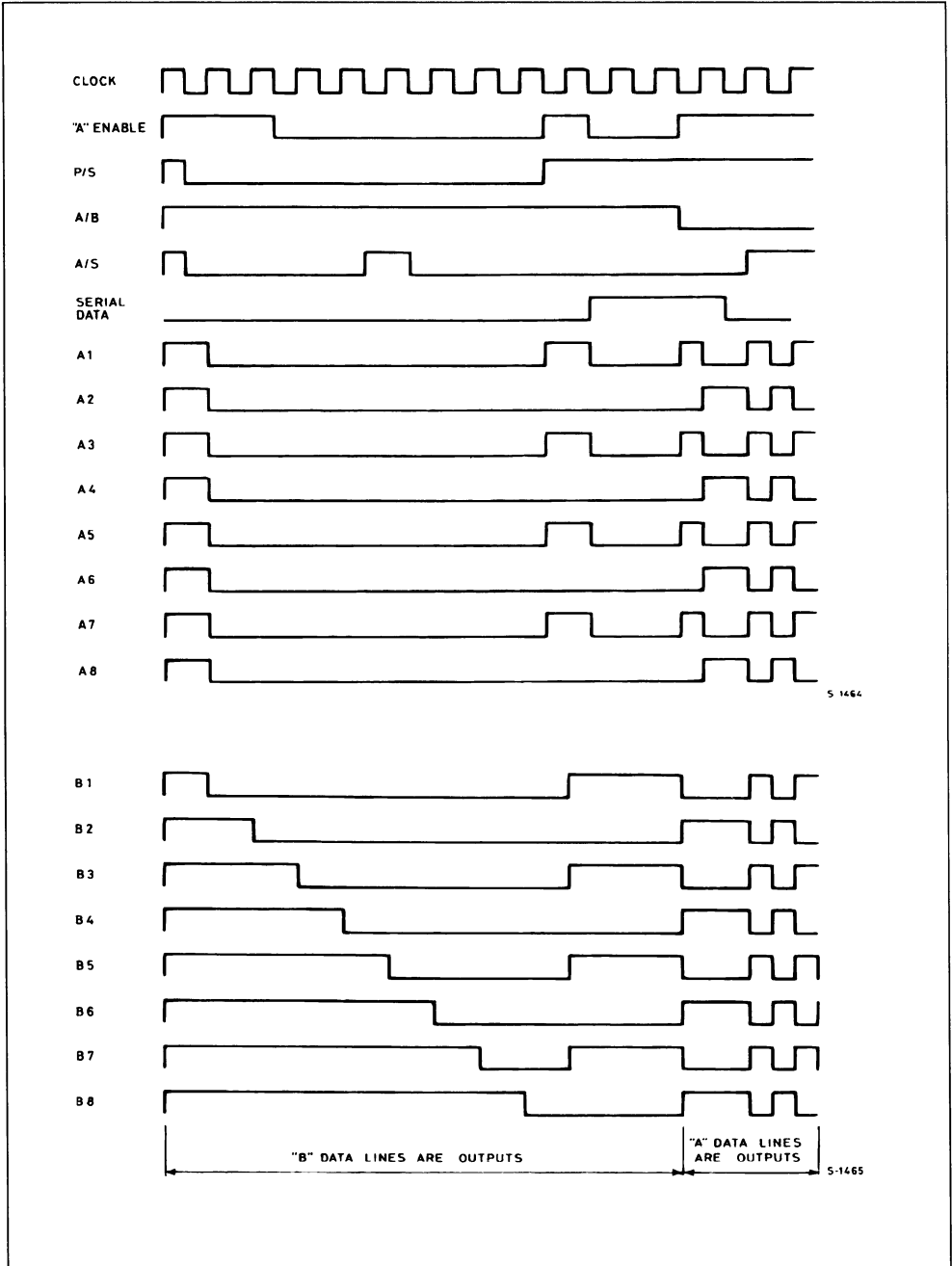


FOR REGISTER INPUT-LEVELS AND RESULTING REGISTER OPERATION

"A" Enable	P/S	A/B	A/S	Operation*
0	0	0	X	Serial Mode ; Synch. Serial Data Input, "A" Parallel Data Outputs Disabled
0	0	1	X	Serial Mode ; Synch. Serial Data Input, "B" Parallel Data Output
0	1	0	0	Parallel Mode ; "B" Synch. Parallel Data Inputs, "A" Parallel Data Outputs Disabled
0	1	0	1	Parallel Mode ; "B" Asynch. Parallel Data Inputs, "A" Parallel Data Outputs Disabled
0	1	1	0	Parallel Mode ; "A" Parallel Data Inputs Disabled, "B" Parallel Data Outputs, Synch. Data Recirculation
0	1	1	1	Parallel Mode ; "A" Parallel Data Inputs Disabled, "B" Parallel Data Outputs, Asynch. Data Recirculation
1	0	0	X	Serial Mode ; Synch. Serial Data Input, "A" Parallel Data Output
1	0	1	X	Serial Mode ; Synch. Serial Data Input, "B" Parallel Data Output
1	1	0	0	Parallel Mode ; "B" Synch. Parallel Data Input, "A" Parallel Data Output
1	1	0	1	Parallel Mode ; "B" Asynch. Parallel Data Input, "A" Parallel Data Output
1	1	1	0	Parallel Mode ; "A" Synch. Parallel Data Input, "B" Parallel Data Output
1	1	1	1	Parallel Mode ; "A" Asynch. Parallel Data Input, "B" Parallel Data Output

* Outputs change at positive transition of clock in the serial mode and when the A/S control inputs is "low" in the parallel mode

TIMING DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Values						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	±10 ⁻⁵	± 0.1		± 1	μA	
		HCF Types	0/15							± 0.3	±10 ⁻⁵	± 0.3		
I _{OH}	3-State Output Leakage Current	HCC Types	0/18	0/18		18		± 0.4	±10 ⁻⁴	± 0.4		± 12	μA	
		HCF Types	0/15	0/15		15		± 1.0	±10 ⁻⁴	± 1.0		± 7.5		
C _I	Input Capacitance		Any Input						5	7.5		pF		

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device

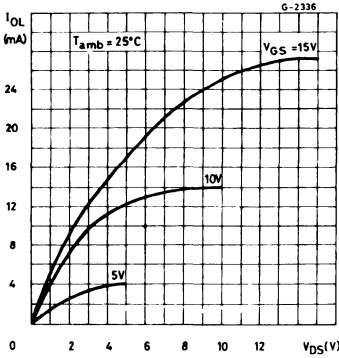
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

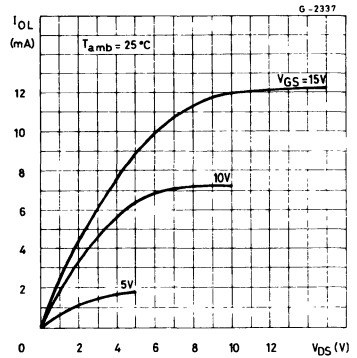
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time : A (B) Parallel Data in to B (A) Parallel Data Out		5		350	700	ns
			10		120	240	
			15		85	170	
t_{PLZ} , t_{PHZ} t_{PZL} , t_{PZH}	3-state Propagation Delay Time A/B or AE to "A" OUT		5		200	400	ns
			10		80	160	
			15		60	120	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Data Setup Time Serial Data to Clock		5		80	160	ns
			10		30	60	
			15		20	40	
	Parallel Data to Clock		5		25	50	ns
			10		15	30	
			15		10	20	
t_w	High-level Pulse Width, AE, P/S, A/S		5		175	350	ns
			10		70	140	
			15		40	80	
f_{CL}	Maximum Clock Frequency		5	2	4		MHz
			10	5	10		
			15	7	14		
t_w	Clock Pulse Width		5		125	250	ns
			10		50	100	
			15		35	70	
t_r , t_f^*	Clock Input Rise or Fall Time		5,10,15			15	μs

* If more than one unit is cascaded, t_r should be made less than or equal to the sum of the transition time and the fixed propagation delay of the output of the driving stage for the estimated capacitive load.

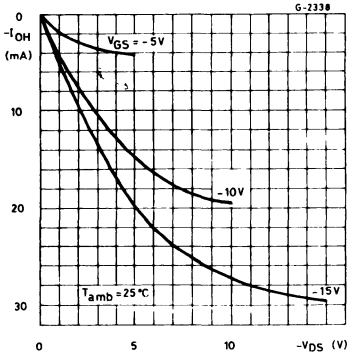
Typical Output Low (sink) Current Characteristics.



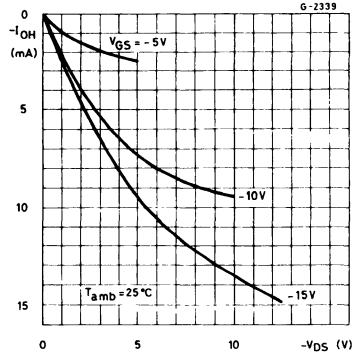
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

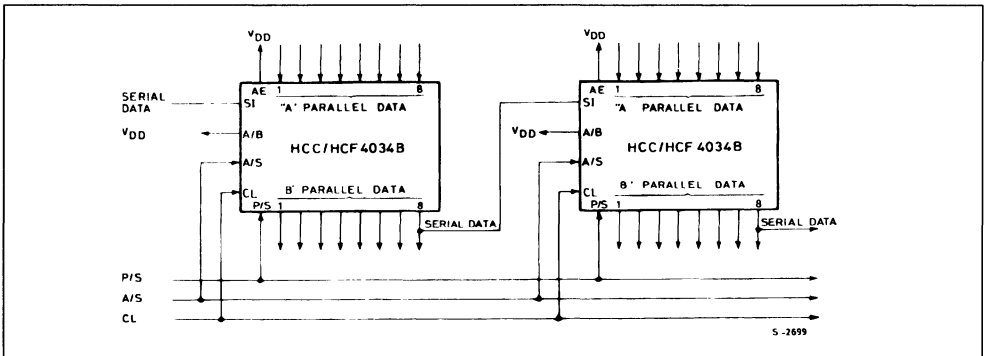


Minimum Output High (source) Current Characteristics.



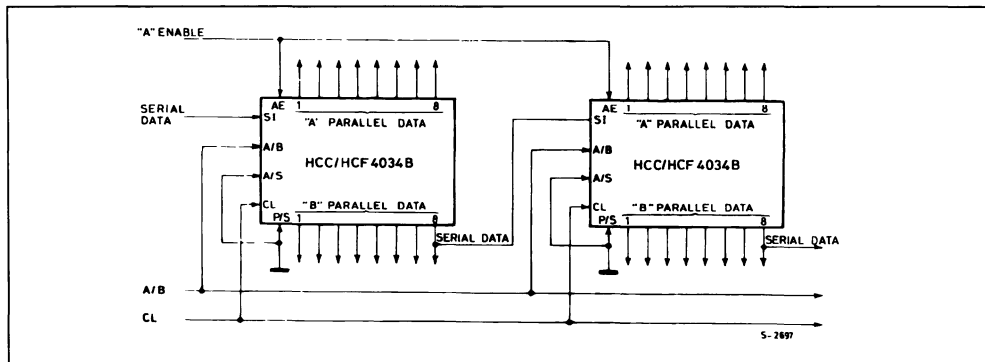
TYPICAL APPLICATIONS

16-BIT PARALLEL IN/PARALLEL OUT PARALLEL IN/SERIAL OUT, SERIAL IN/PARALLEL OUT, SERIAL IN/SERIAL OUT REGISTER.

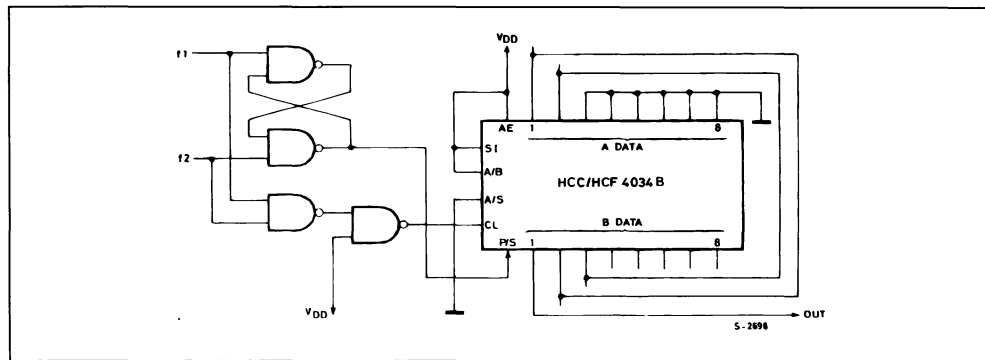


TYPICAL APPLICATIONS (continued)

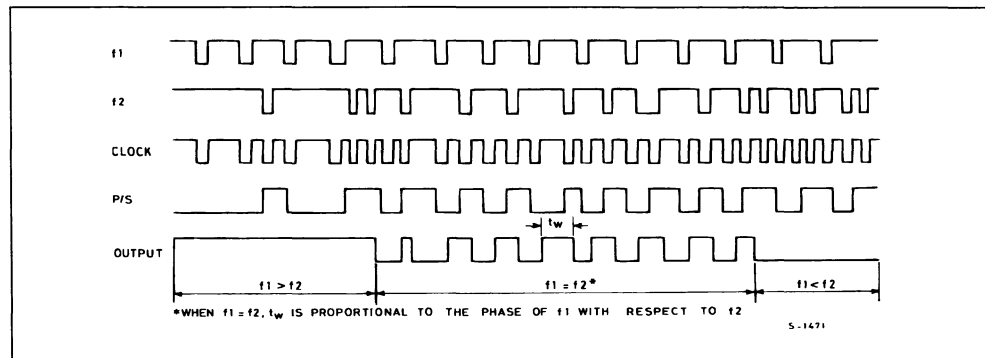
16-BIT SERIAL IN/GATED PARALLEL OUT REGISTER



FREQUENCY AND PHASE COMPARATOR.

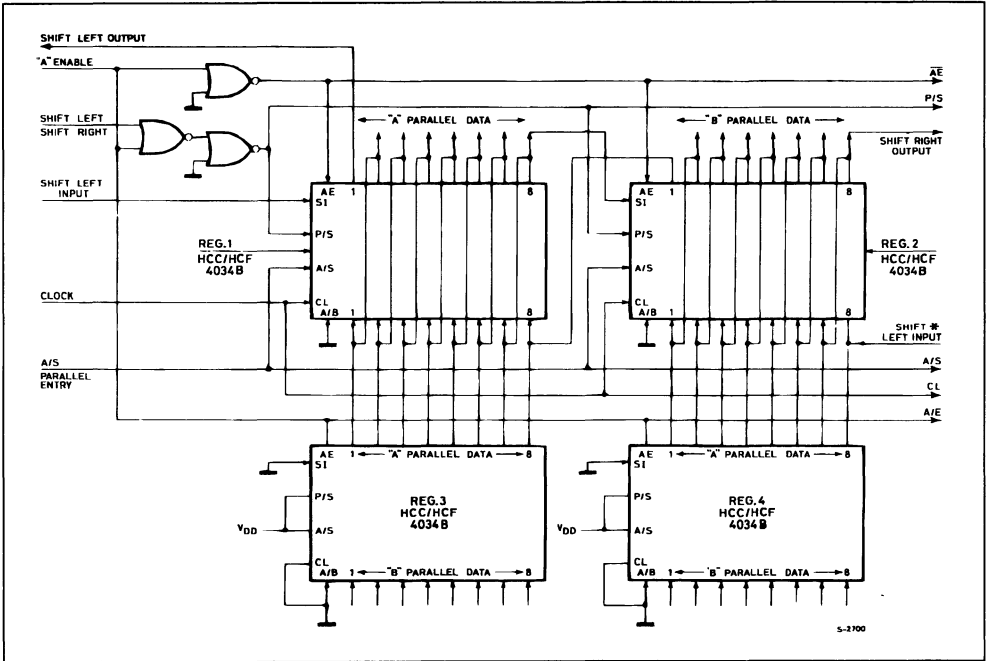


TIMING DIAGRAM



TYPICAL APPLICATIONS (continued)

SHIFT RIGHT/SHIFT LEFT WITH PARALLEL INPUTS

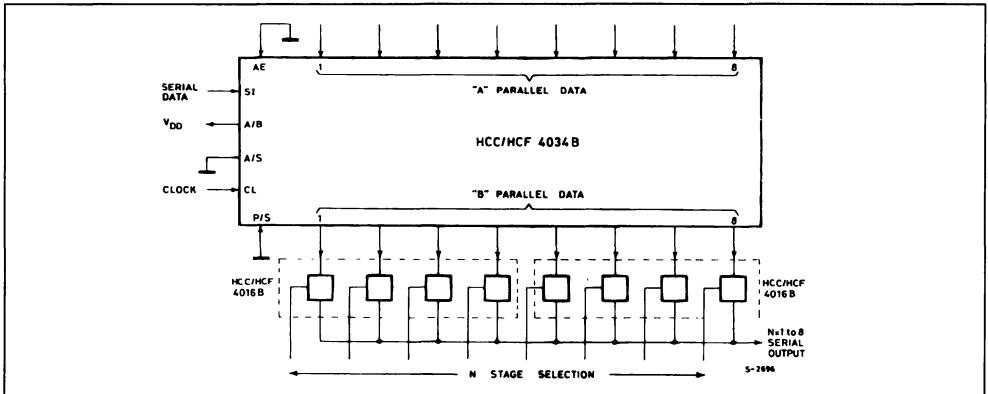


A "High" ("Low") on the Shift Left/Shift Right input allows serial data on the Shift Left Input (Shift Right Input) to enter the register on the positive transition of the clock signal. A "high" on the "A" Enable Input disables the "A" parallel data lines on Reg. 1 and 2 and enables the "A" data lines on registers 3 and 4 and allows parallel data into registers 1 and 2. Other

logic schemes may be used in place of registers 3 and 4 for parallel loading. When parallel inputs are not used Reg. 3 and 4 and associated logic are not required.

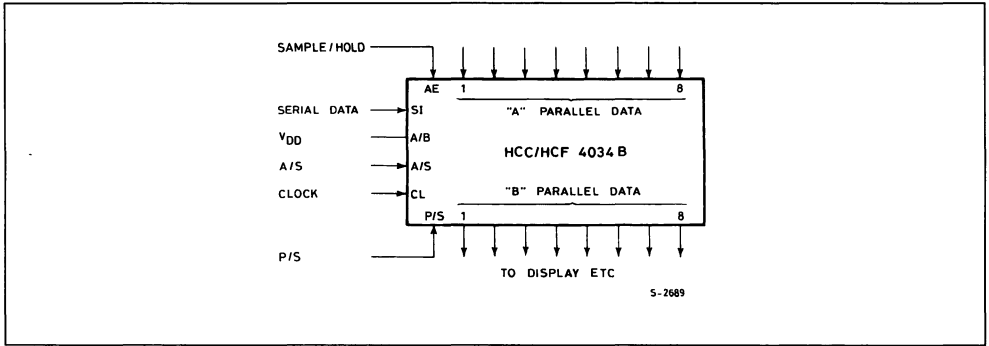
* Shift Left input must be disabled during parallel entry.

N-STAGE REGISTER WITH FIXED SERIAL OUTPUT LINE

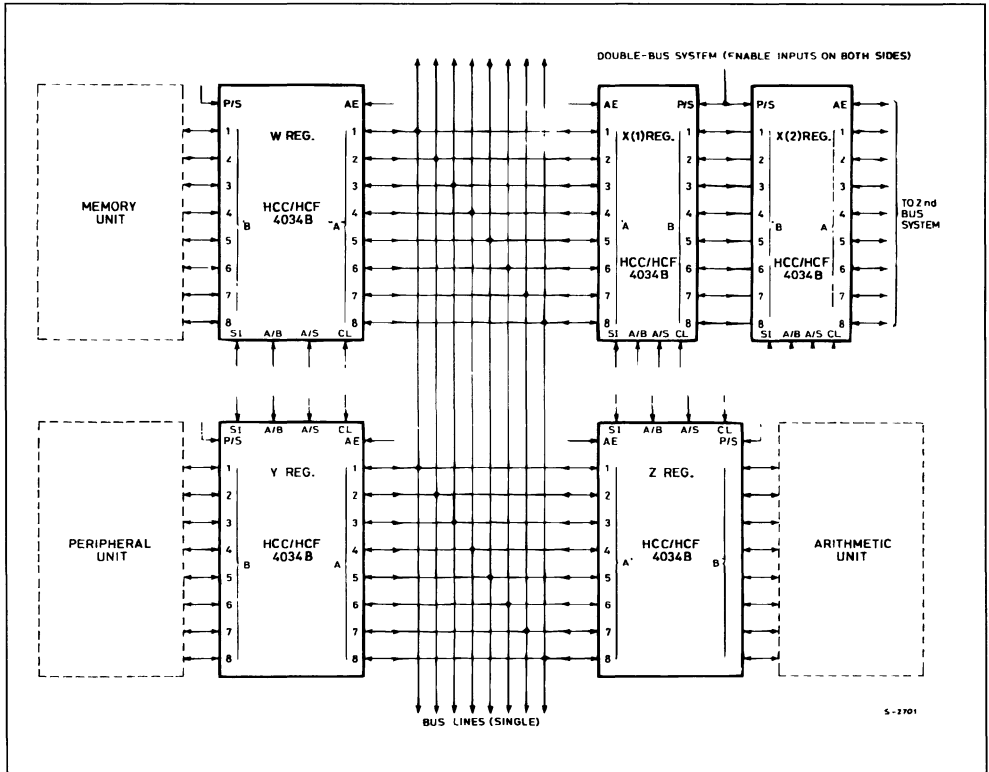


TYPICAL APPLICATIONS (continued)

SAMPLE AND HOLD REGISTER-SERIAL/PARALLEL IN-PARALLEL OUT



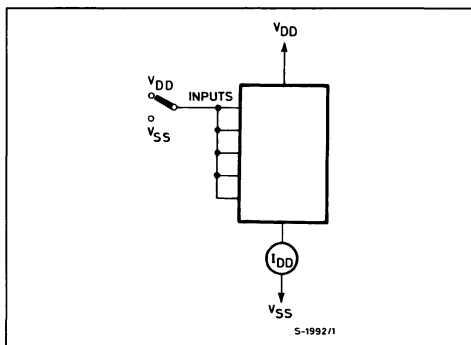
SINGLE-AND DOUBLE-BUS SYSTEMS



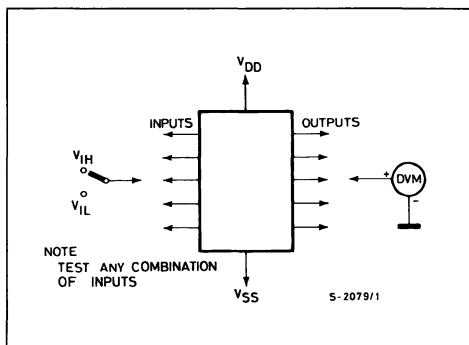
The "A" enable (AE) and A/B signals control all combinations of transfer between the registers and bus systems

TEST CIRCUITS

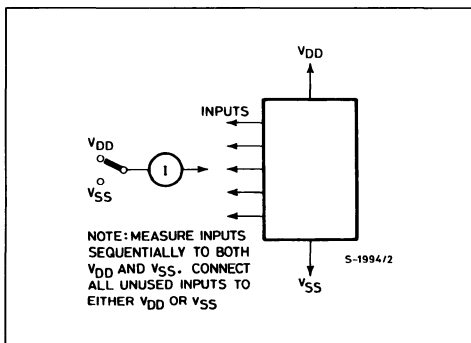
Quiescent Device Current.



Noise Immunity.



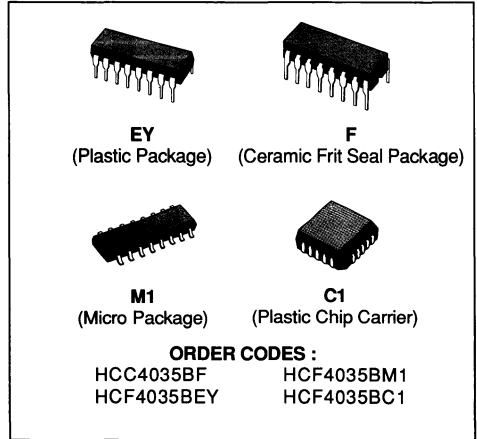
Input Leakage Current.



4-STAGE PARALLEL IN/PARALLEL OUT SHIFT REGISTER

- 4-STAGE CLOCKED SHIFT OPERATION
- SYNCHRONOUS PARALLEL ENTRY ON ALL 4 STAGES
- JK INPUTS ON FIRST STAGE
- ASYNCHRONOUS TRUE/COMPLEMENT CONTROL ON ALL OUTPUTS
- STATIC FLIP-FLOP OPERATION ; MASTER-SLAVE CONFIGURATION
- BUFFERED INPUTS AND OUTPUTS
- HIGH SPEED 12MHz (typ.) AT $V_{DD} = 10V$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURR 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

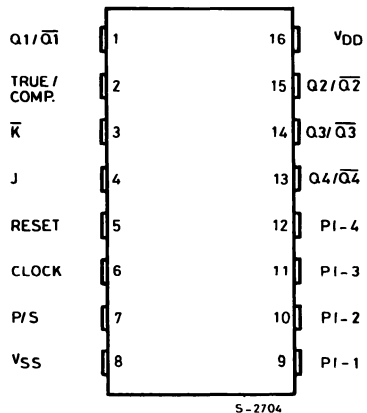
When \bar{K} inputs connected together, the first stage becomes a D flip-flop. An asynchronous common RESET is also provided.



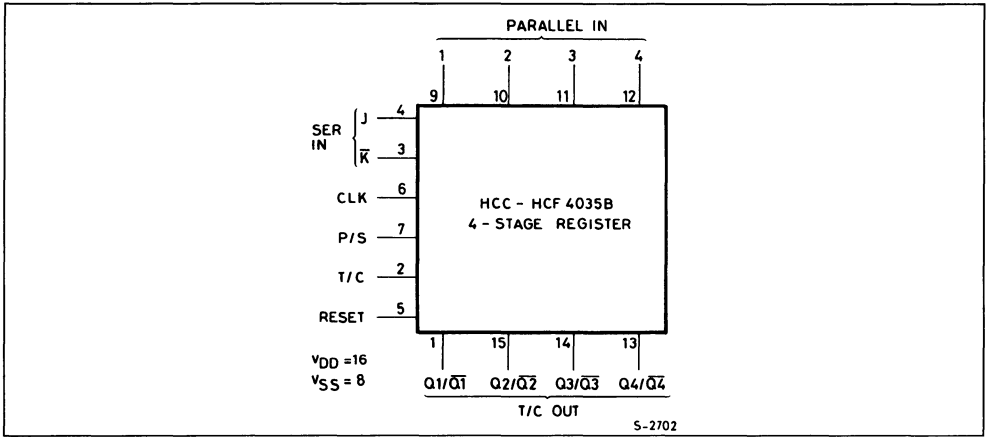
DESCRIPTION

The **HCC4035B** (extended temperature range) and **HCF4035B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4035B** is a four-stage clocked signal serial register with provision for synchronous PARALLEL inputs to each stage and SERIAL inputs to the first stage via JK logic. Register stages 2, 3, and 4 are coupled in a serial D flip-flop configuration when the register is in the serial mode (PARALLEL/SERIAL control low). Parallel entry into each register stage is permitted when the PARALLEL/SERIAL control is high. In the parallel or serial mode information is transferred on positive clock transitions. When the TRUE/COMPLEMENT control is high, the true contents of the register are available at the output terminals. When the TRUE/COMPLEMENT control is low, the outputs are the complements of the data in the register. The TRUE/COMPLEMENT control functions asynchronously with respect to the CLOCK signal. JK input logic is provided on the first stage SERIAL input to minimize logic requirements particularly in counting and sequence-generation applications.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

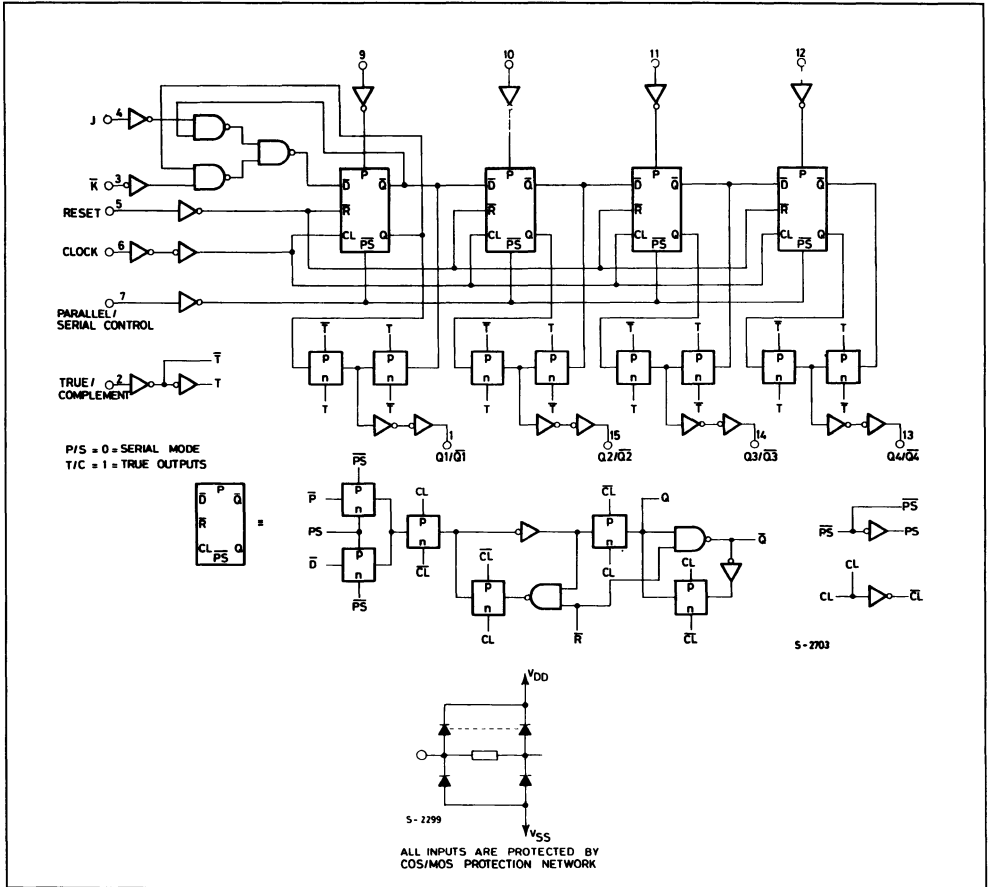
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C

LOGIC DIAGRAM



TRUTH TABLE
FIRST STAGE

Clock (ø)	t _{n-1} (inputs)				t _n (outputs)
	J	K	R	Q _{n-1}	Q _n
	0	X	0	0	0
	1	X	0	0	1
	X	0	0	1	0
	1	0	0	Q _{n-1}	$\overline{Q_{n-1}}$ Toggle Mode
	X	1	0	1	1
	X	X	0	Q _{n-1}	Q _{n-1}
X	X	X	1	X	0

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
	HCF Types	0/ 5			5		20		0.04	20		150		
		0/10			10		40		0.04	40		300		
		0/15			15		80		0.4	80		600		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μA	
		HCF Types	0/15		15		± 0.3		±10 ⁻⁵	± 0.3		± 1		
C _I	Input Capacitance	Any Input							5	7.5			pF	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device.

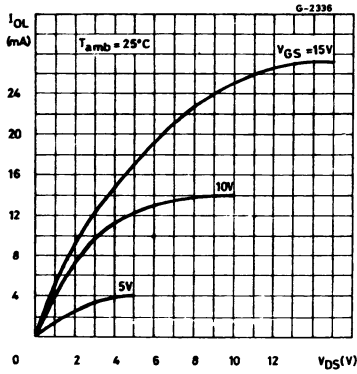
* T_{High} = + 125°C for HCC device . + 85°C for HCF device

The Noise Margin for both "1" and "0" level is : 1V min with V_{DD} = 5 V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

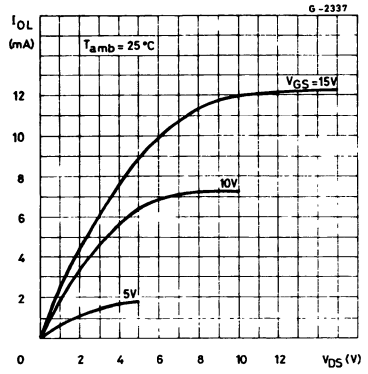
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t_{PLH} , t_{PHL}	Propagation Delay Time		5		250	500	ns
			10		100	200	
			15		75	150	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}	Maximum Clock Input Frequency		5	2	4		MHz
			10	6	12		
			15	8	16		
t_w	Clock Pulse Width		5		100	200	ns
			10		45	90	
			15		30	60	
t_r , t_f	Clock Input Rise or Fall Time		5		15		μs
			10		15		
			15		15		
t_{setup}	Data Setup Time J/K Lines		5		110	220	ns
			10		40	80	
			15		30	60	
t_{setup}	Data Setup Time Parallel-In-Lines		5		70	140	ns
			10		25	50	
			15		20	40	
RESET OPERATION							
t_{PLH} , t_{PHL}	Propagation Delay Time		5		230	460	ns
			10		100	200	
			15		80	160	
t_w	Reset Pulse Width		5		125	250	ns
			10		55	110	
			15		40	40	

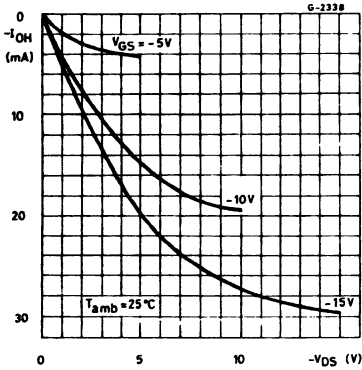
Typical Output Low (sink) Current Characteristics.



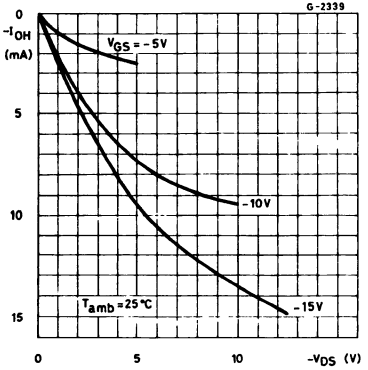
Minimum Output Low (sink) Current Characteristics.



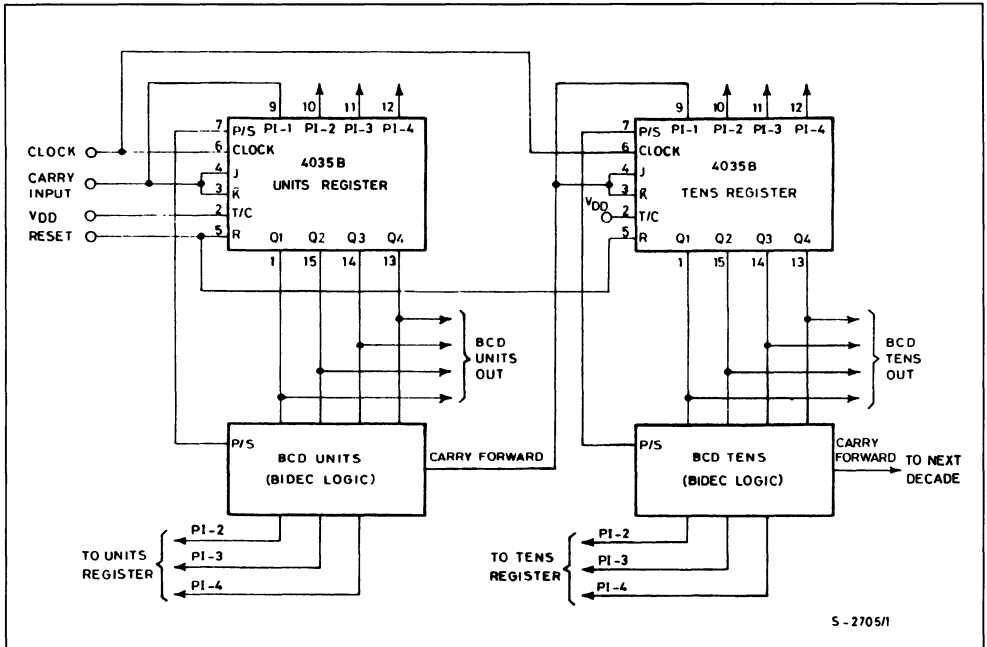
Typical Output High (source) Current Characteristics.



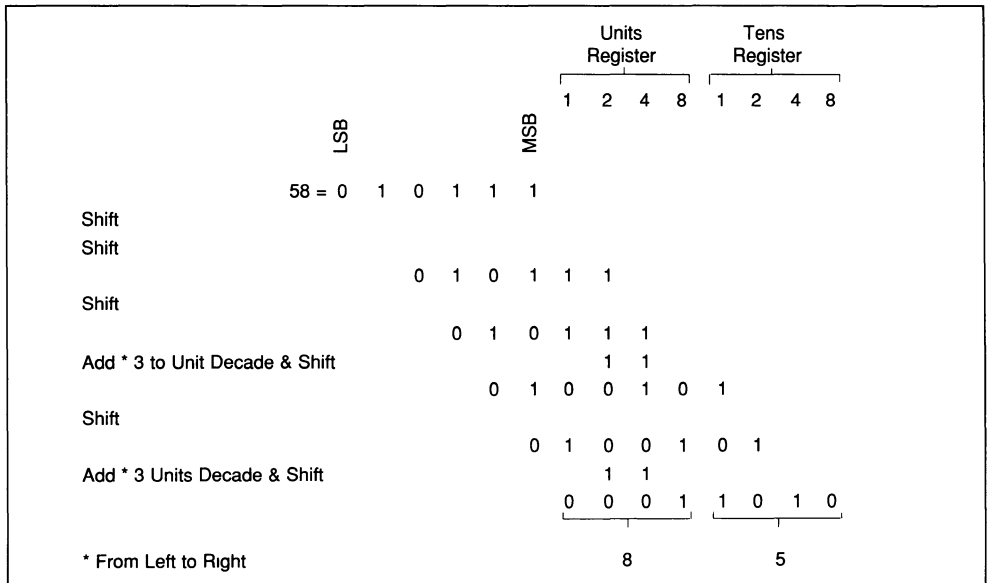
Minimum Output High (source) Current Characteristics.



TYPICAL APPLICATIONS
BINARY-TO-BCD CONVERTER

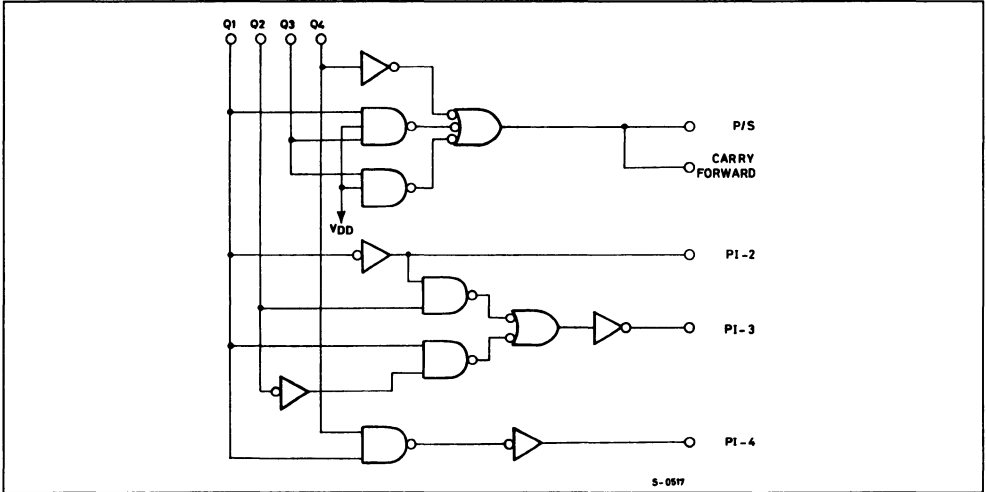


EXAMPLE OF BINARY-TO-BCD CONVERSION



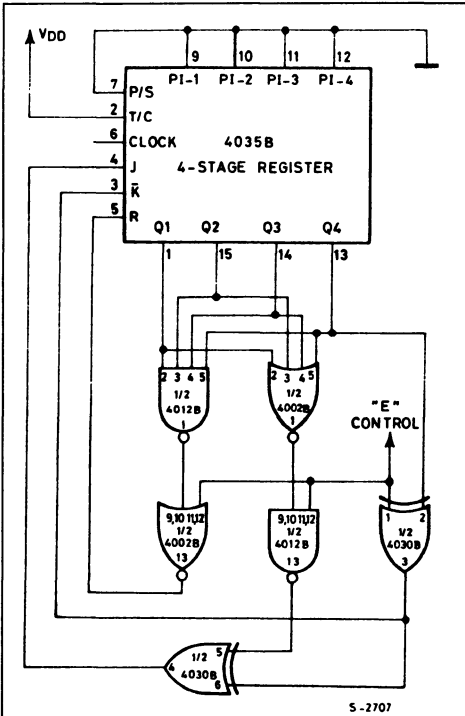
TYPICAL APPLICATIONS

BIDEC LOGIC



S-0677

DOUBLE SEQUENCE GENERATOR



S-2707

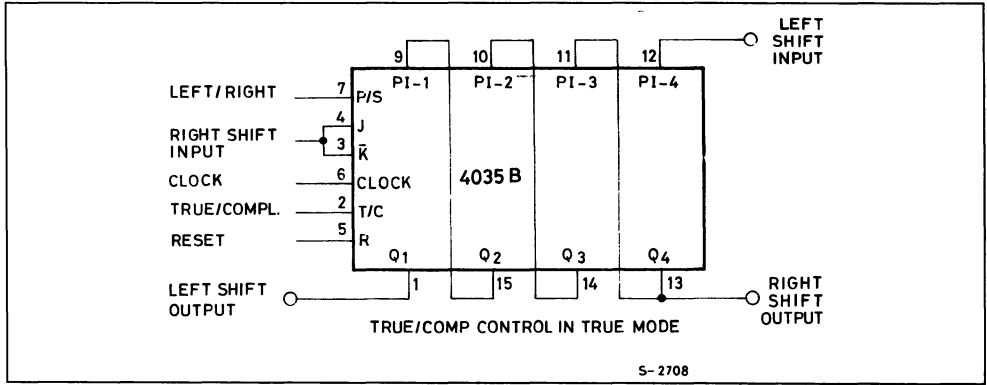
STATE SEQUENCES

Using a control line (E) two different state sequences can be generated. For example, suppose the following two sequences are desired on command (control line E).

	Control = E = 0				1			
	Q ₁	Q ₂	Q ₃	Q ₄	Q ₁	Q ₂	Q ₃	Q ₄
0	A	B	C	D	15	1	1	1
1	1	0	0	0	14	0	0	1
2	0	1	0	0	13	1	0	1
5	1	0	1	0	10	0	1	0
10	0	1	0	1	5	1	0	1
4	0	0	1	0	11	1	1	0
9	1	0	0	1	6	0	1	1
3	1	1	0	0	12	0	0	1
6	0	1	1	0	9	1	0	0
13	1	0	1	1	2	0	1	0
11	1	1	0	1	4	0	0	1
7	1	1	1	0	8	0	0	0
14	0	1	1	1	1	1	0	0
12	0	0	1	1	3	1	1	0
8	0	0	0	1	7	1	1	0

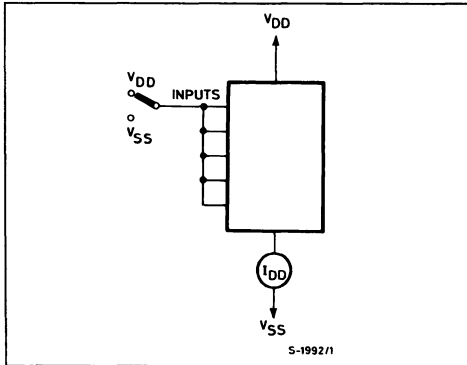
TYPICAL APPLICATIONS

SHIFT LEFT/SHIFT RIGHT REGISTER

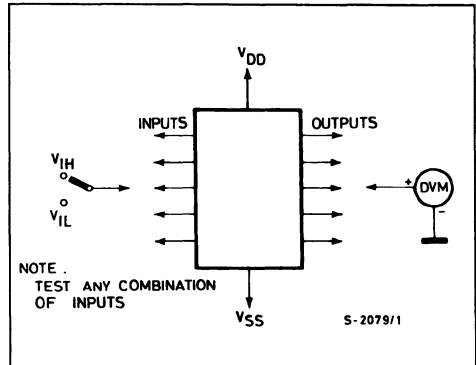


TEST CIRCUITS

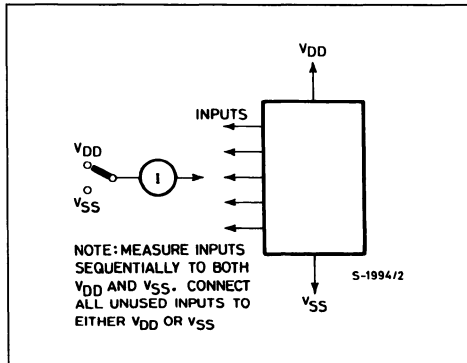
Quiescent Device Current.



Input Voltage.

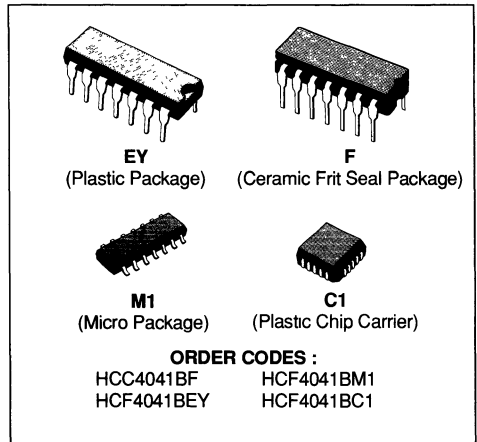


Input Current.



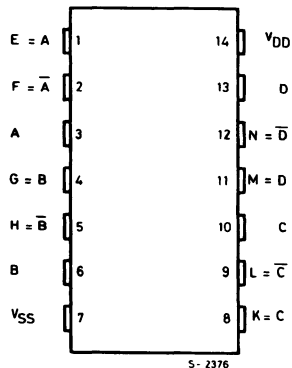
QUAD TRUE/COMPLEMENT BUFFER

- BALANCED SINK AND SOURCE CURRENT ; APPROXIMATELY 4 TIMES STANDARD "B" DRIVE
- EQUALIZED DELAY TO TRUE AND COMPLEMENT OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100 % TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

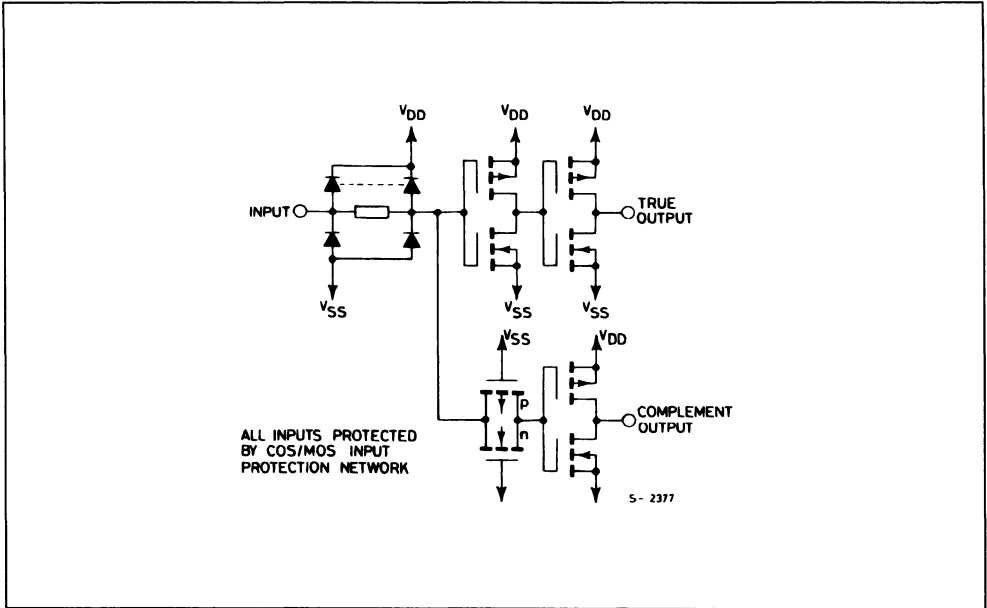

DESCRIPTION

The **HCC4041UB** (extended temperature range) and **HCF4041UB** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4041UB** types are quad true/complement buffers consisting of n- and p-channel units having low channel resistance and high current (sourcing and sinking) capability. The **HCC/HCF4041UB** is intended for use as a buffer, line driver, or COS/MOS-to-TTL driver. It can be used as an ultra-low power resistor-network driver for A/D and D/A conversion, as a transmission-line driver, and in other applications where high noise immunity and low-power dissipation are primary design requirements.

PIN CONNECTIONS


SCHEMATIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V_I (V)	V_O (V)	$ I_{O} $ (μ A)	V_{DD} (V)	T_{Low}^*		25°C			T_{High}^*			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I_L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
		HCF Types	0/20			20		20		0.04	20		600	
			0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V_{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V_{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V_{IH}	Input High Voltage		0.5/4.5	< 1	5	4		4			4		V	
			1/9	< 1	10	8		8			8			
			1.5/13.5	< 1	15	12.5		12.5			12.5			

* T_{Low} = -55°C for HCC device : -40°C for HCF device.

* T_{High} = +125°C for HCC device : +85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1			1		1	V
			9/1	< 1	10		2			2		2	
			13.5/1.5	< 1	15		2.5			2.5		2.5	
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 8.4		- 6.4	- 12.8		- 4.6	mA
			0/ 5	4.6		5	- 2.1		- 1.6	- 3.2		- 1.2	
			0/10	9.5		10	- 6.25		- 5	- 10		- 3.5	
			0/15	13.5		15	- 24		- 19	- 38		- 13	
		HCF Types	0/ 5	2.5		5	- 6.8		- 5.44	- 12.8		- 4.08	
			0/ 5	4.6		5	- 1.7		- 1.36	- 3.2		- 1.02	
			0/10	9.5		10	- 5.31		- 4.25	- 10		- 3.18	
		0/15	13.5		15	- 20.13		- 16.15	- 38		- 12.11		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	2.1		1.6	3.2		1.2	
			0/10	0.5		10	6.25		5	10		3.5	
			0/15	1.5		15	24		19	38		13	
		HCF Types	0/ 5	0.4		5	1.7		1.36	3.2		1.02	
			0/10	0.5		10	5.31		4.25	10		3.18	
			0/15	1.5		15	20.13		16.15	38		12.11	
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						15	22.5		pF	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device

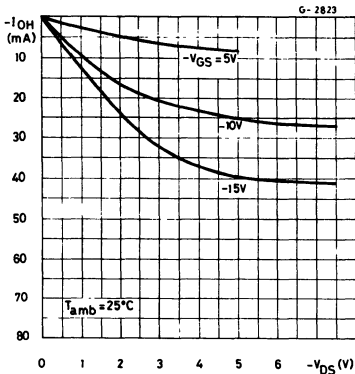
* T_{High} = + 125°C for HCC device + 85°C for HCF device

The Noise Margin for both "1" and "0" level is \geq 1V min with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

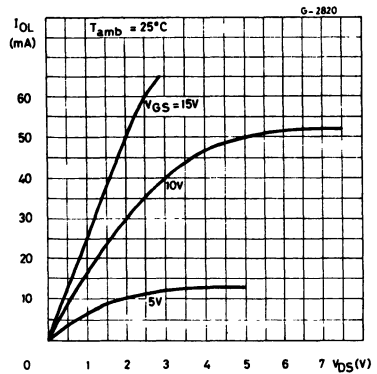
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3 %/°C, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time		5		60	120	ns
			10		35	70	
			15		25	50	
t _{THL} , t _{TLH}	Transition Time		5		40	80	ns
			10		20	40	
			15		15	30	

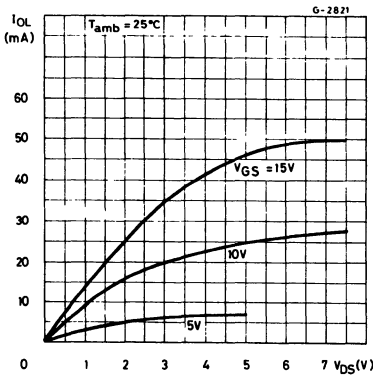
Minimum Output High (source) Current Characteristics.



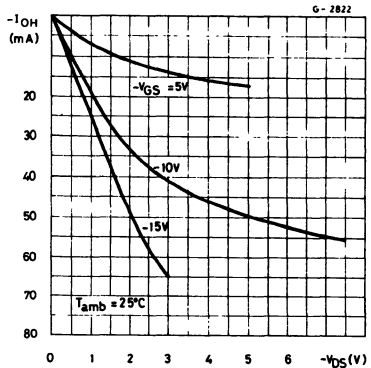
Typical Output Low (sink) Current.



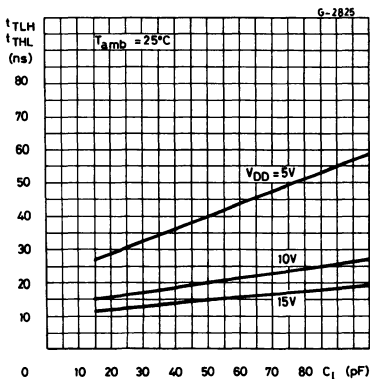
Minimum Output Low (sink) Current Characteristics.



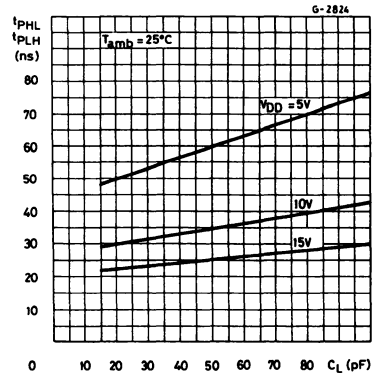
Typical Output High (source) Current Characteristics.



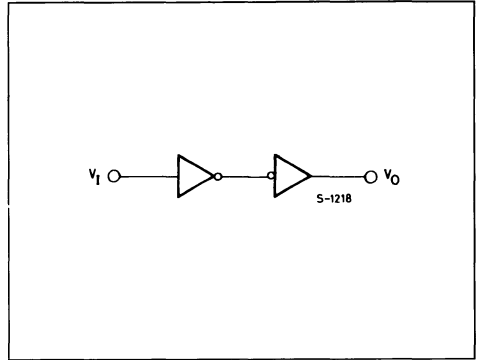
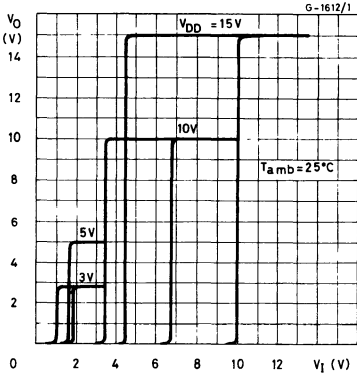
Typical Transition Time vs. Load Capacitance.



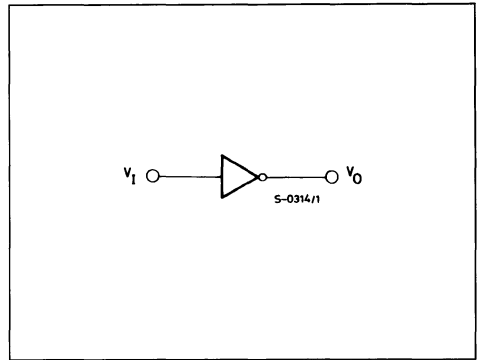
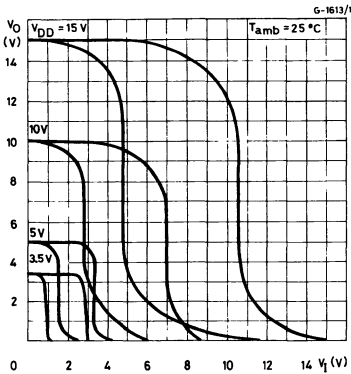
Typical Propagation Delay Time vs. Load Capacitance.



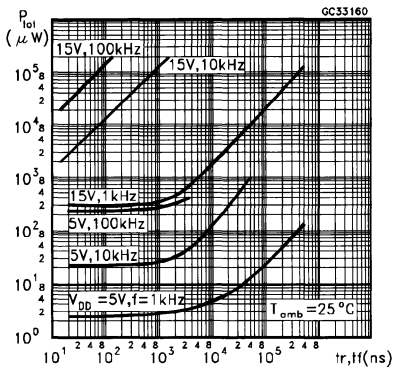
Minimum and Maximum Transfer Characteristics-true Output-and Test Circuit.



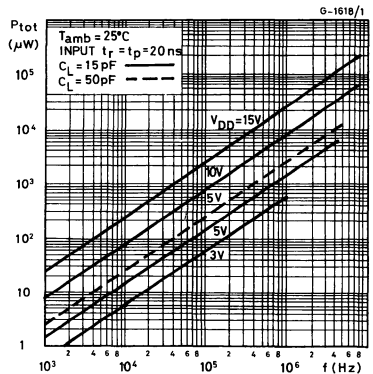
Minimum Maximum Transfer Characteristics Complement Output-and Test Circuit.



Typical Power Dissipation vs. Input Rise and Fall Time per Output Pair.

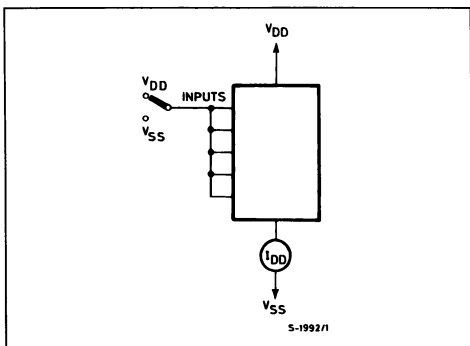


Typical Power Dissipation vs. Frequency per Output Pair.

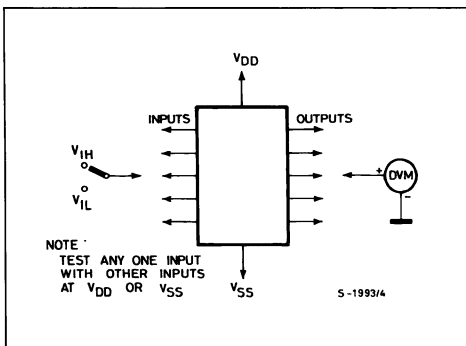


TEST CIRCUITS

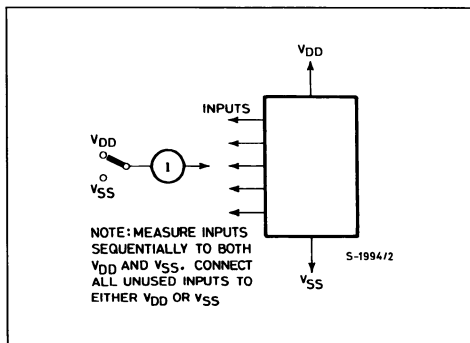
Quiescent Device Current.



Noise Immunity.

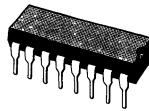
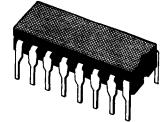
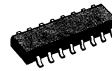


Input Leakage Current.



QUAD CLOCKED "D" LATCH

- CLOCK POLARITY CONTROL
- Q AND \bar{Q} OUTPUTS
- COMMON CLOCK
- LOW POWER TTL COMPATIBLE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


EY
 (Plastic Package)

F
 (Ceramic Package)

M1
 (Micro Package)

C1
 (Plastic Chip Carrier)

ORDER CODES :

 HCC4042BF
 HCF4042BEY

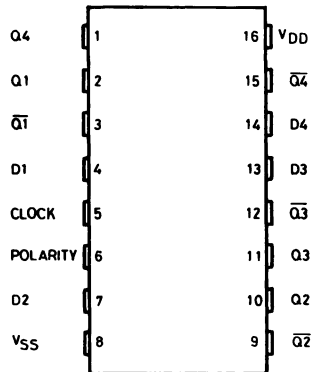
 HCF4042BM1
 HCF4042BC1

DESCRIPTION

The **HCC4042B** (extended temperature range) and **HCF4042B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

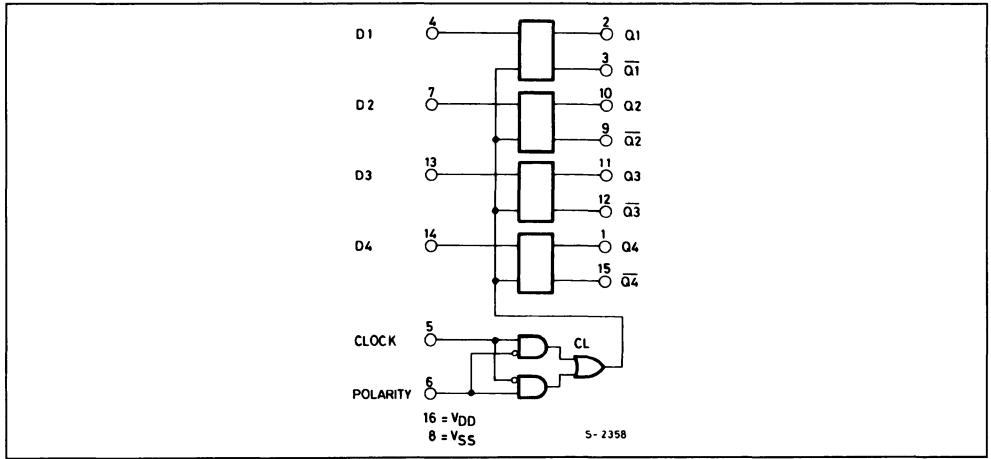
The **HCC/HCF4042B** types contain four latch circuits, each strobed by a common clock. Complementary buffered outputs are available from each circuit. The impedance of the n- and p-channel output devices is balanced and all outputs are electrically identical.

Information present at the data input is transferred to outputs Q and \bar{Q} during the CLOCK level which is programmed by the POLARITY input. For POLARITY = 0 the transfer occurs during the 0 CLOCK level and for POLARITY = 1 the transfer occurs during the 1 CLOCK level. The outputs follow the data input providing the CLOCK and POLARITY levels defined above are present. When a CLOCK transition occurs (positive for POLARITY = 0 and negative for POLARITY = 1) the information present at the input during the CLOCK transition is retained at the outputs until an opposite CLOCK transition occurs.

PIN CONNECTIONS


S-2361

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

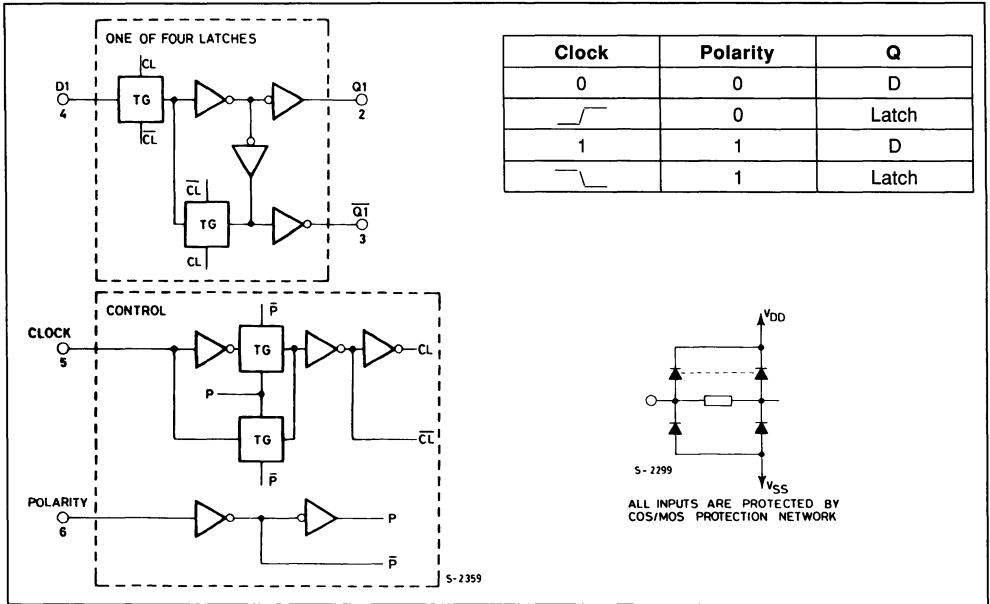
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage HCC Types : HCF Types	3 to 18 3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C

LOGIC BLOCK DIAGRAM AND TRUTH TABLE



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5		1	0.02	1		30	μ A	
			0/10			10		2	0.02	2		60		
			0/15			15		4	0.02	4		120		
		0/20			20	20		0.04	20		600			
		HCF Types	0/5				5		4	0.02	4			30
			0/10				10		8	0.02	8			60
0/15					15		16	0.02	16		120			
V _{OH}	Output High Voltage	0/5	< 1	5	5	4.95		4.95		4.95		V		
		0/10	< 1	10	10	9.95		9.95		9.95				
		0/15	< 1	15	15	14.95		14.95		14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5	5		0.05		0.05		0.05	V		
		10/0	< 1	10	10		0.05		0.05		0.05			
		15/0	< 1	15	15		0.05		0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5		3.5		V		
			1/9	< 1	10	7		7		7				
			1.5/13.5	< 1	15	11		11		11				

* T_{Low} = -55°C for HCC device, -40°C for HCF device.* T_{High} = +125°C for HCC device; +85°C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36	
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9	
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4	
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1	
			0/5	4.6		5	-0.52		-0.44	-1		-0.36	
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9	
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5		pF	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is . 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

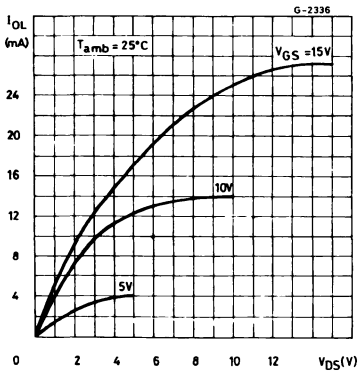
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

Symbol	Parameter		Test Conditions			Value			Unit
				V _{DD} (V)		Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time	Data in to Q		5		110	220	ns	
				10		55	110		
				15		40	80		
			Data in to \bar{Q}		5		150		300
					10		75		150
					15		50		100
		Clock to Q		5		225	450		
				10		100	200		
				15		80	160		
		Clock to \bar{Q}		5		250	500		
				10		115	230		
				15		90	180		

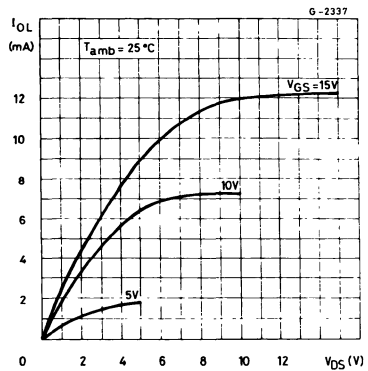
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{THL} , t _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t _w	Clock Pulse Width		5	200	100		ns
			10	100	50		
			15	60	30		
t _{setup}	Setup Time		5	50	0		ns
			10	30	0		
			15	25	0		
t _{hold}	Hold Time		5	120	60		ns
			10	60	30		
			15	50	25		
t _r , t _f	Clock Input Rise or Fall Time		5	Not Rise or Fall Time Sensitive			μs
			10				
			15				

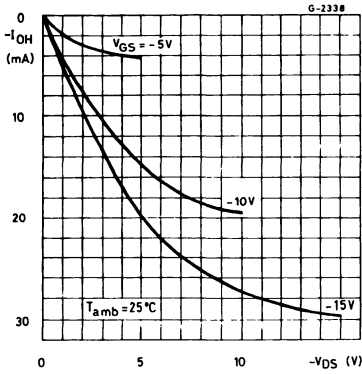
Typical Output Low (sink) Current Characteristics.



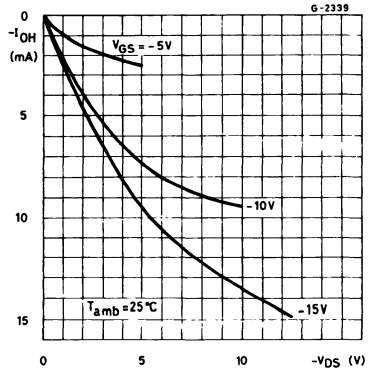
Minimum Output Low (sink) Current Characteristics.



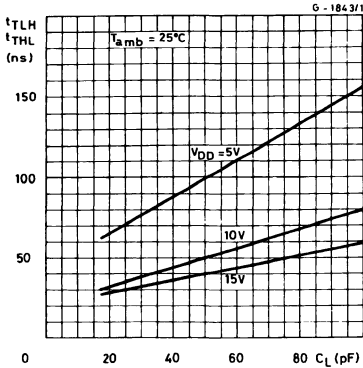
Typical Output High (source) Current Characteristics.



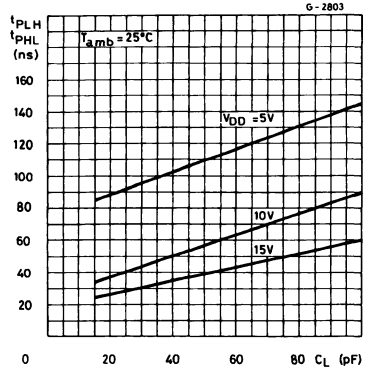
Minimum Output High (source) Current Characteristics.



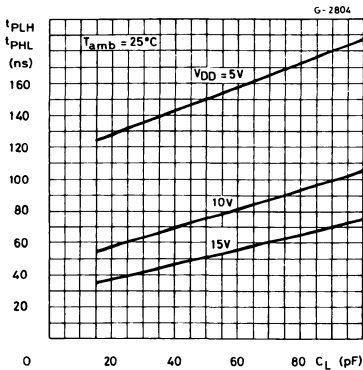
Typical Transition Time vs. Load Capacitance.



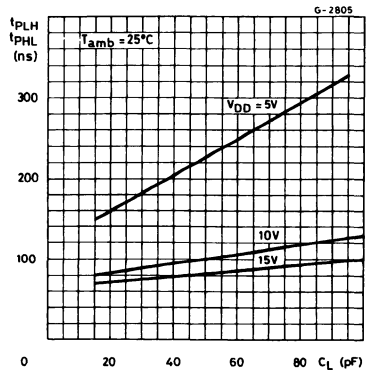
Typical Propagation Delay Time vs. Load Capacitance (data to Q).



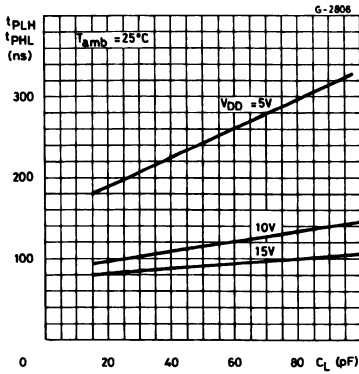
Typical Propagation Delay Time vs. Load Capacitance (data to Q).



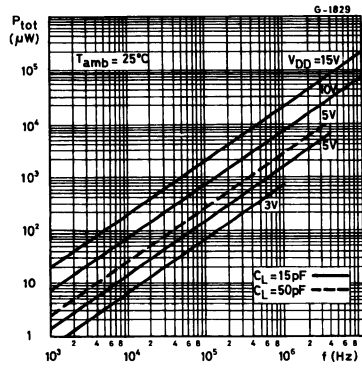
Typical Propagation Delay Time vs. Load Capacitance (clock to Q).



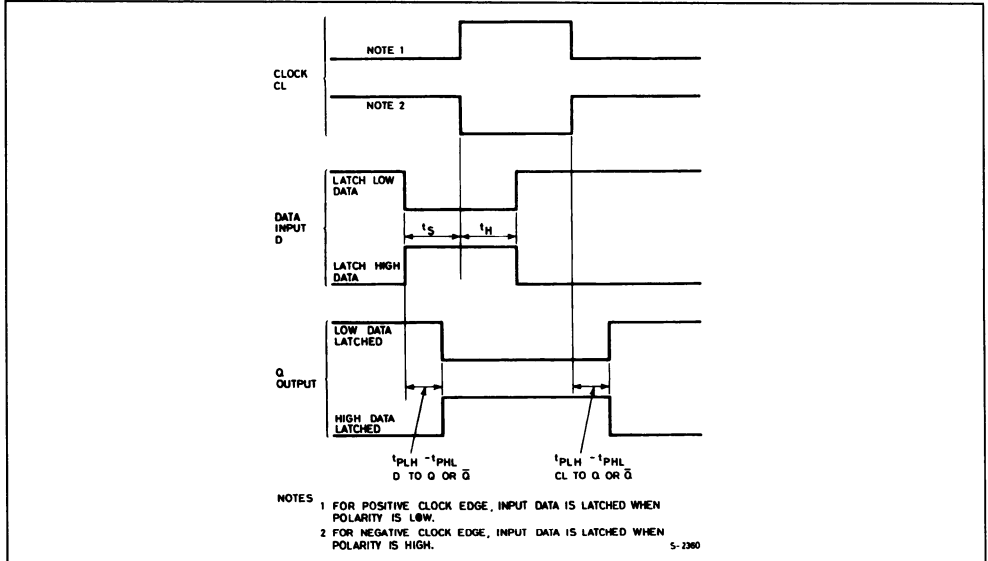
Typical Propagation Delay Time vs. Load Capacitance (clock to Q).



Typical Power Dissipation/device vs. Frequency.

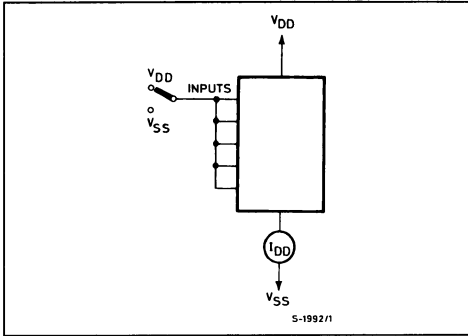


Dynamic Test Parameters.

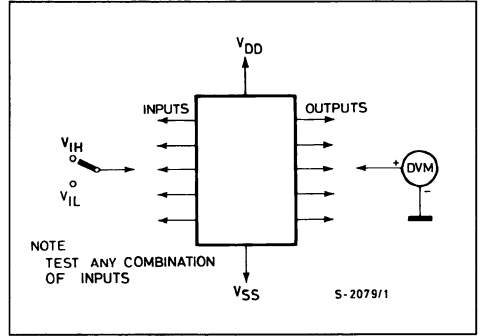


TEST CIRCUITS

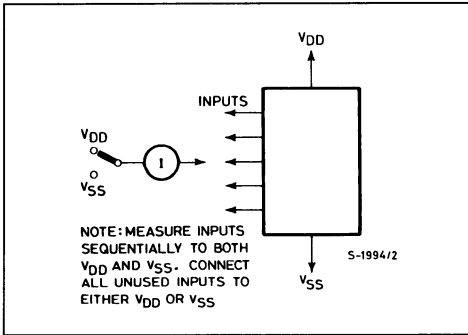
Quiescent Device Current.



Noise Immunity.



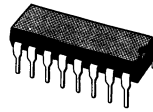
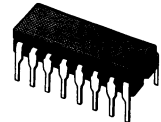
Input Leakage Current.



QUAD 3-STATE R-S LATCHES

QUAD NOR R-S LATCH-4043B
QUAD NAND R-S LATCH-4044B

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 3-LEVEL OUTPUTS WITH COMMON OUTPUT ENABLE
- SEPARATE SET AND RESET INPUT FOR EACH LATCH
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- NOR AND NAND CONFIGURATIONS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


EY
 (Plastic Package)

F
 (Ceramic Frit Seal Package)

M1
 (Micro Package)

C1
 (Plastic Chip Carrier)

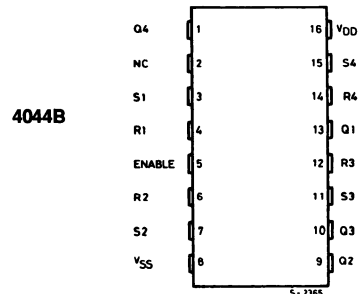
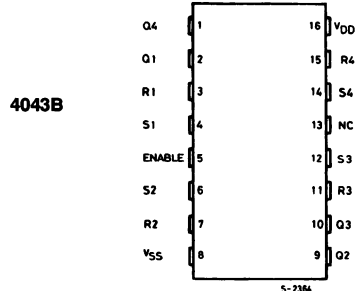
ORDER CODES :

HCC40XXBF	HCF40XXBM1
HCF40XXBEY	HCF40XXBC1

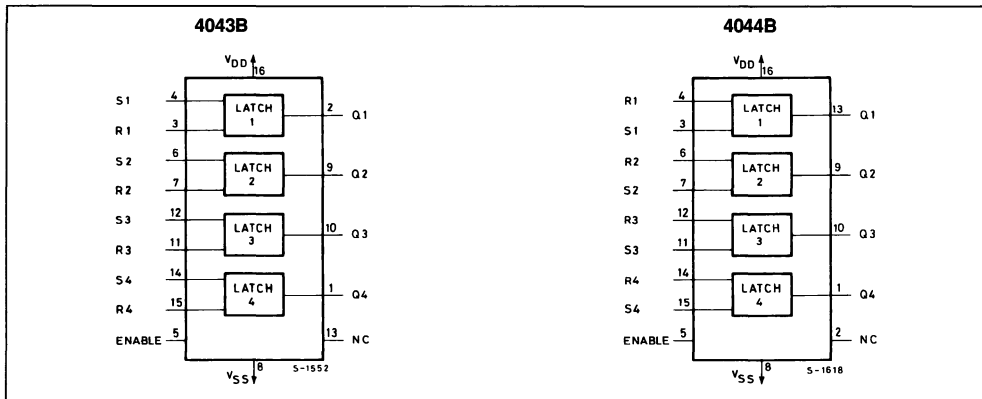
DESCRIPTION

The **HCC4043B**, **HCC4044B**, (extended temperature range) and the **HCF4043B**, **HCF4044B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4043B** types are quad cross-coupled 3-state COS/MOS NOR latches and the **HCC/HCF4044B** types are quad cross-coupled 3-state COS/MOS NAND latches. Each latch has a separate Q output and individual SET and RESET inputs. The Q outputs are controlled by a common ENABLE input. A logic "1" or "high" on the ENABLE input connects the latch states to the Q outputs. A logic "0" or "low" on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common bussing of the outputs.

PIN CONNECTIONS



FUNCTIONAL DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

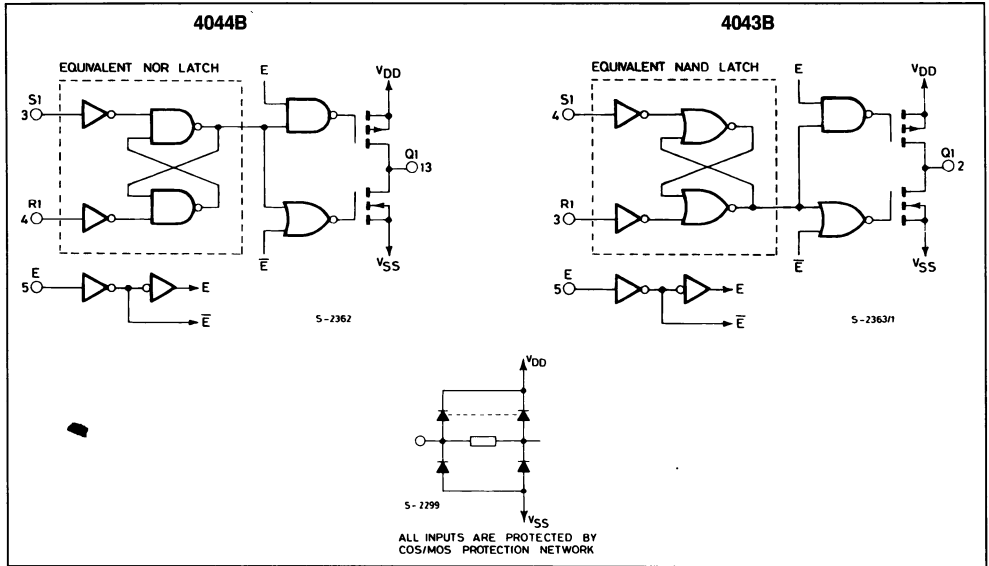
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5		5		1	0.02	1		30	μA	
			0/10		10		2	0.02	2		60		
			0/15		15		4	0.02	4		120		
		HCF Types	0/20		20		20	0.04	20		600		
			0/ 5		5		4	0.02	4		30		
			0/10		10		8	0.02	8		60		
0/15		15		16	0.02	16		120					
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95			4.95	V		
		0/10	< 1	10	9.95		9.95			9.95			
		0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05	0.05	V		
		10/0	< 1	10		0.05			0.05	0.05			
		15/0	< 1	15		0.05			0.05	0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5		3.5	V		
			1/9	< 1	10	7		7		7			
			1.5/13.5	< 1	15	11		11		11			

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36	
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9	
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1	
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36	
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15										
I _{OH}	3-state Output	HCC Types	0/18	0/18	18		\pm 0.4		\pm 10 ⁻⁴	\pm 0.4		\pm 12	μ A
		HCF Types	0/15	0/15	15		\pm 1.0		\pm 10 ⁻⁴	\pm 1.0		\pm 7.5	
C _I	Input Capacitance		Any Input						5	7.5		pF	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

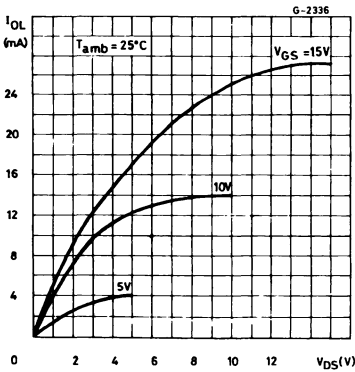
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time (SET or RESET to Q)		5		150	300	ns
			10		70	140	
			15		50	100	
t _{PZH} , t _{PHZ}	3-state Propagation Delay Time (ENABLE to Q)		5		115	230	ns
			10		55	110	
			15		40	80	

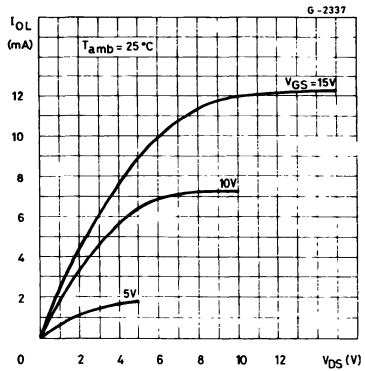
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)	Min.	Typ.	Max.		
t_{PLZ}, t_{PZL}	Propagation Delay Time	5		90	180	ns	
		10		50	100		
		15		35	70		
t_{TLH}, t_{THL}	Transition Time	5		100	200	ns	
		10		50	100		
		15		40	80		
t_w	Pulse Width (SET or RESET)	5	160	80		ns	
		10	80	40			
		15	40	20			

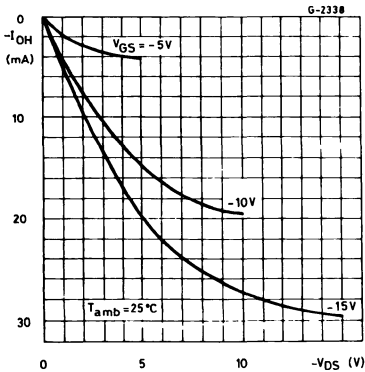
Typical Output Low (sink) Current.



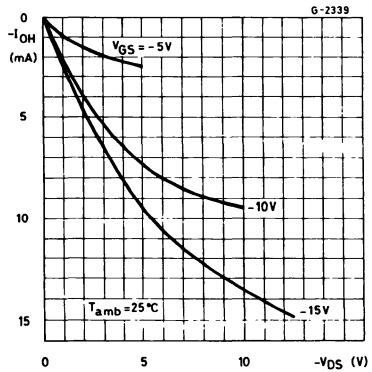
Minimum Output Low (sink) Current Characteristics.



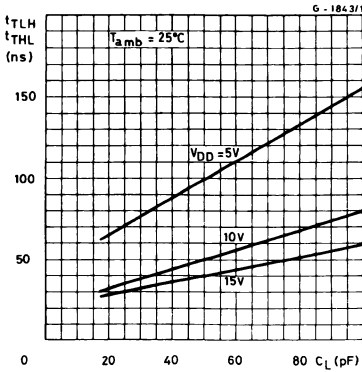
Typical Output High (source) Current Characteristics.



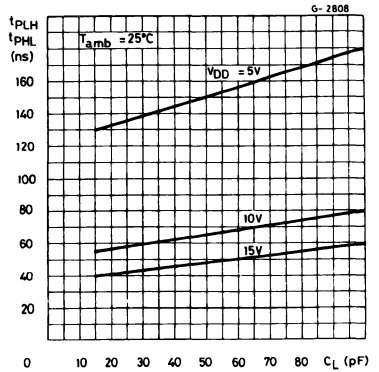
Minimum Output High (source) Current Characteristics.



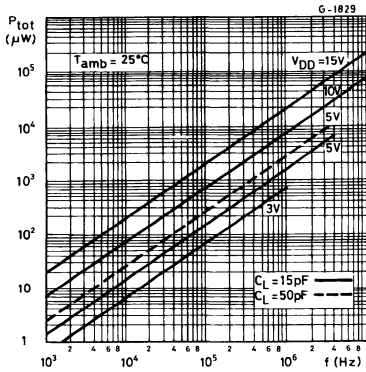
Typical Transition Time vs. Load Capacitance.



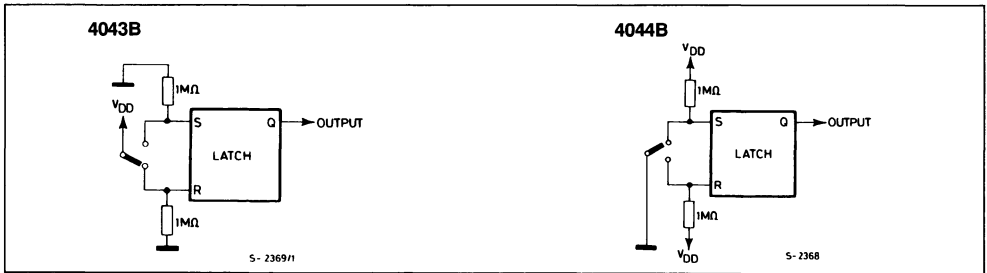
Typical Propagation Delay Time vs. Load Capacitance (SET, RESET to Q).



Typical Power Dissipation/device vs. Frequency.

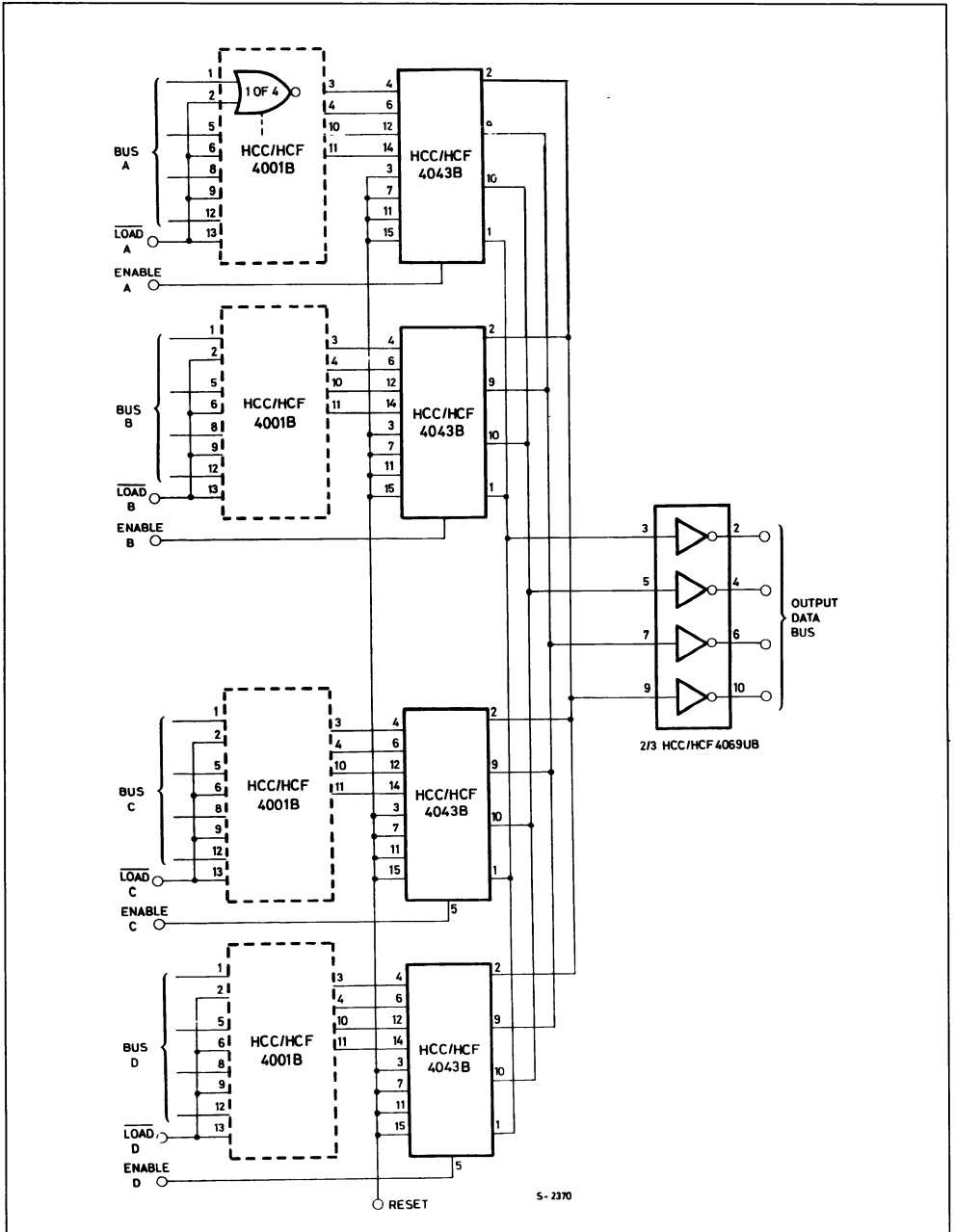


Switch Bounce Eliminator.



APPLICATIONS

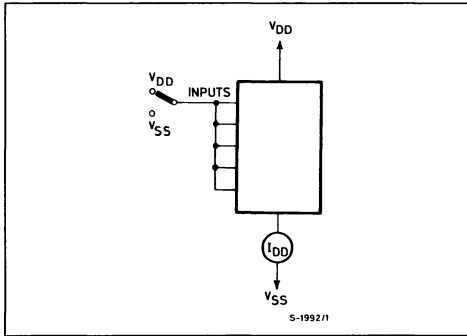
MULTIPLE BUS STORAGE.



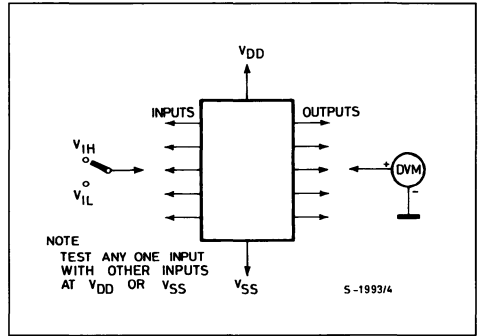
S-2370

TEST CIRCUITS

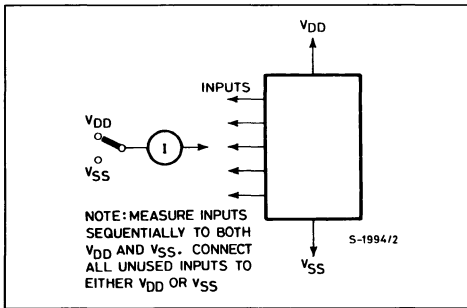
Quiescent Device Current.



Input Voltage.



Input Current.



Enable Propagation Delay Time and Waveforms.

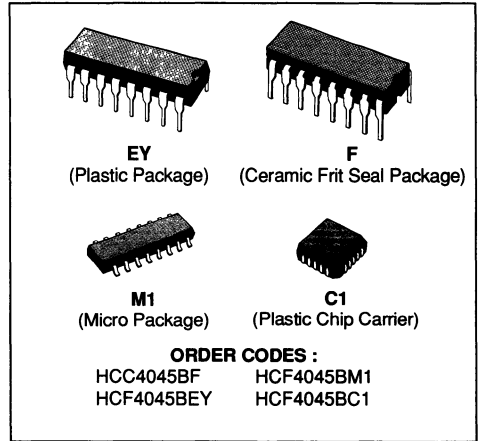
Waveform parameters:
 POINT A (IN = V_{DD}, \bar{IN} = V_{SS}): t_{PZH} (10% to 90%), t_{PHZ} (90% to 10%)
 POINT A (IN = V_{SS}, \bar{IN} = V_{DD}): t_{PLZ} (90% to 10%), t_{PZL} (10% to 90%)

Test	IN	\bar{IN}	A
t _{PHZ}	V _{DD}	V _{SS}	V _{SS}
t _{PLZ}	V _{SS}	V _{DD}	V _{DD}
t _{PZH}	V _{DD}	V _{SS}	V _{SS}
t _{PZL}	V _{SS}	V _{DD}	V _{DD}

Z = High impedance

21-STAGE COUNTER

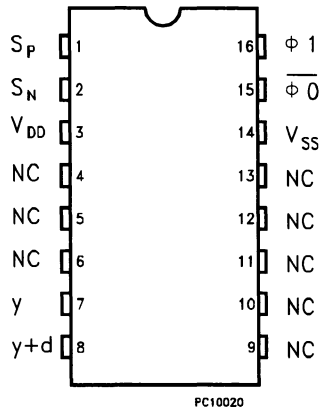
- VERY LOW OPERATING DISSIPATION....
1mW (typ.) ; @ $V_{DD} = 5V$, $f_{\phi} = 1MHz$
- OUTPUT DRIVERS WITH SINK OR SOURCE CAPABILITY....7mA (typ.) @ $V_{DD} = 5V$
- MEDIUM SPEED (typ.).... $f_{\phi} = 16MHz$, @ $V_{DD} = 10V$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



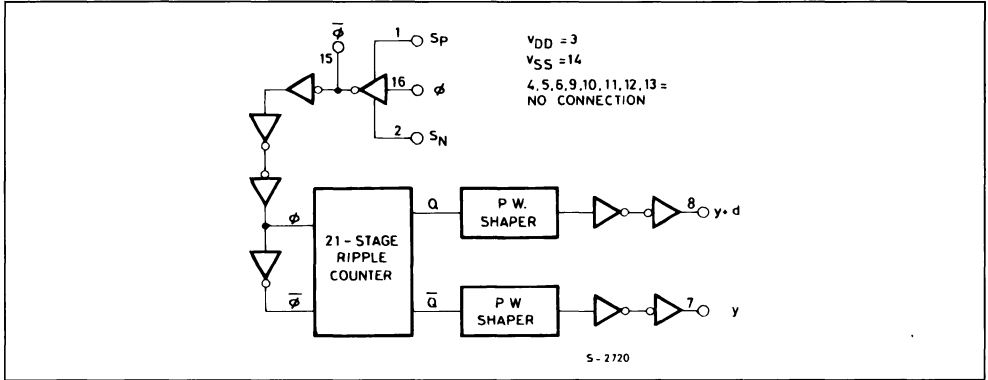
DESCRIPTION

The **HCC4045B** (extended temperature range) and **HCF4045B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4045B** is a timing circuit consisting of 21 counter stages, two output-shaping flip-flops, two inverter output drivers, and input inverters for use in a crystal oscillator. The **HCC/HCF4045B** configuration provides 21 flip-flop counting stages, and two flip-flops for shaping the output waveform for a 3.125% duty cycle. Push-pull operation is provided by the inverter output drivers. The first inverter is intended for use as a crystal oscillator-amplifier. However, it may be used as a normal logic inverter if desired. A crystal oscillator circuit can be made less sensitive to voltage-supply variations by the use of source resistors. In this device, the sources of the p and n transistors have been brought out to package terminals. If external resistors are not required, the sources must be shorted to their respective substrates (S_p to V_{DD} , S_n to V_{SS}).

PIN CONNECTIONS



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

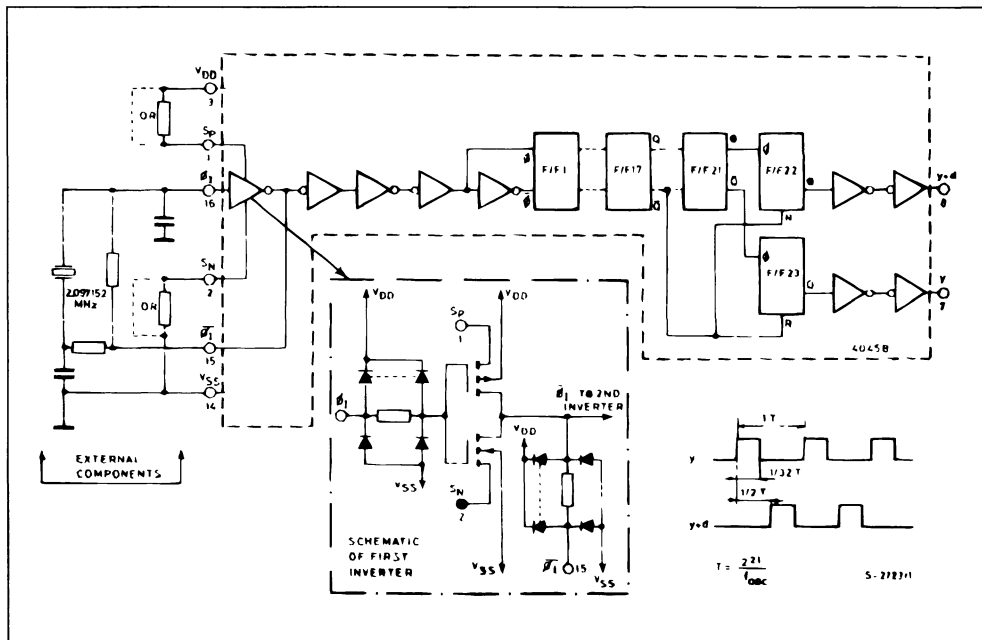
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
 * All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

LOGIC DIAGRAM

4045B and Outboard Components in a Typical 21-stage Counter Application.



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C		T _{High} *				
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		

* T_{Low} = - 55°C for HCC device - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	4.6		5	-4.5		-3.6	-7		-2.5	mA	
			0/10	9.5		10	-11.2		-9.1	-18		-6.3		
			0/15	13.5		15	-29.4		-23.8	-47		-16.8		
		HCF Types	0/5	4.6		5	-3.6		-3	-7		-2.46		
			0/10	9.5		10	-8.9		-7.7	-18		-6.54		
			0/15	13.5		15	-23.8		-20	-47		-16.6		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	4.5		3.6	7		2.5	mA	
			0/10	0.5		10	11.2		9.1	18		6.3		
			0/15	1.5		15	29.4		23.8	47		16.8		
		HCF Types	0/5	0.4		5	3.6		3	7		2.46		
			0/10	0.5		10	8.9		7.7	18		6.54		
			0/15	1.5		15	23.8		20	47		16.6		
I _{IH} , I _{IL}	Input Laekage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} = 0.3%/°C values, all input rise and fall times = 20ns)

Symbol	Parameter		Test Conditions		Value			Unit
				V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time ϕ to y or y + d Out			5		2.2	5.5	μ s
				10		0.9	2.7	
				15		0.65	2	
t _{THL} , t _{TLH}	Transition Time			5		25	50	ns
				10		13	25	
				15		10	20	
f _{max}	Maximum Input Pulse Frequency External Pulse Source			5	5	10		MHz
				10	12	25		
				15	15	30		

DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _w	Input Pulse Width		5		50	100	ns
			10		25	50	
			15		20	40	
t _r , t _f	Clock Input Rise or Fall Time		5			500	μs
			10			500	
			15			500	
	Variation of Output Frequency (unit to unit)	f = 5MHz	5		0.05		%
			10		0.03		
			15		0.1		
RC OSCILLATOR OPERATION							
f _{osc}	Maximum Oscillator Frequency (see fig. below left)	R _X = 50KΩ R _S = 560KΩ C _X = 50pF	5	45	60	75	KHz
			10	45	60	75	
			15	45	60	75	

TYPICAL APPLICATIONS

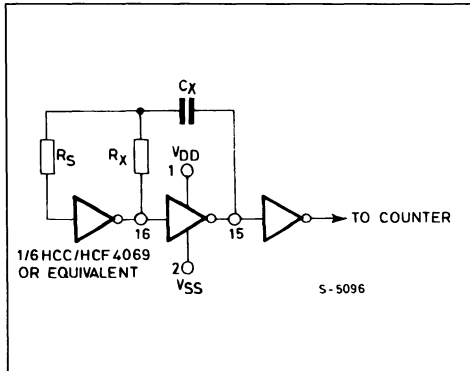
Digital equipment in which ultra-low dissipation and/or operation using a battery source are primary design requirements.

Accurate timing from a crystal oscillator for timing applications such as wall clocks, table clocks, automobile clocks, and digital timing references in

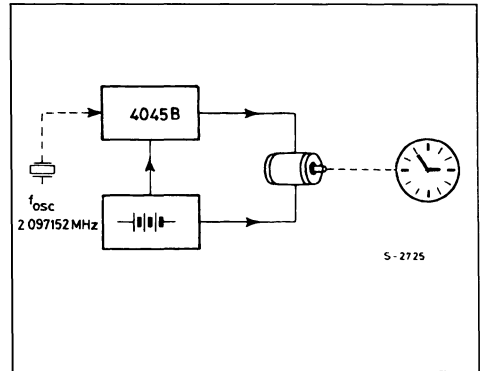
any circuit requiring accurately timed outputs at various intervals in the counting sequence.

Driving miniature synchronous motors, stepping motors, or external bipolar transistors in push-pull fashion.

Typical RC Circuit.

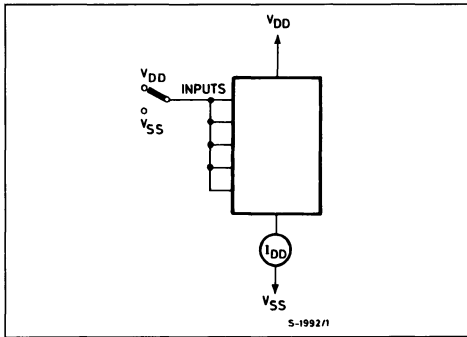


Electronic Watch Application Circuit.

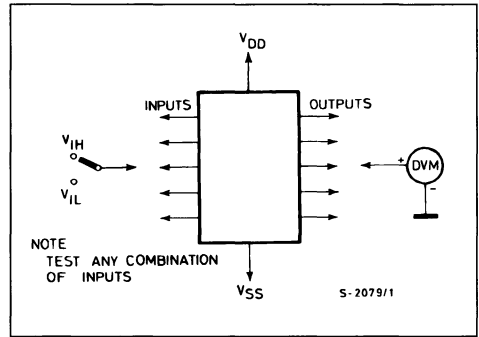


TEST CIRCUITS

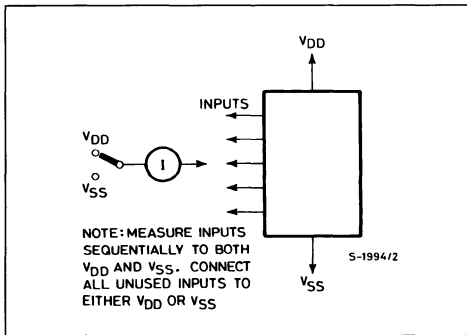
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.

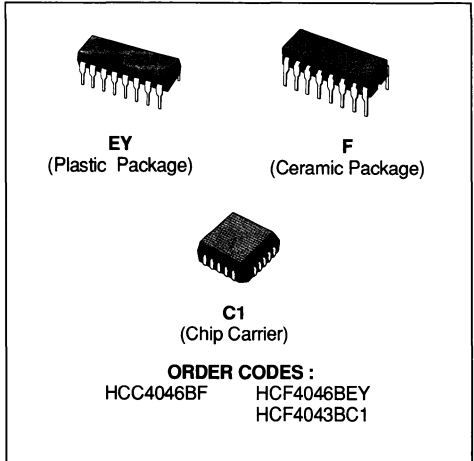


MICROPOWER PHASE-LOCKED LOOP

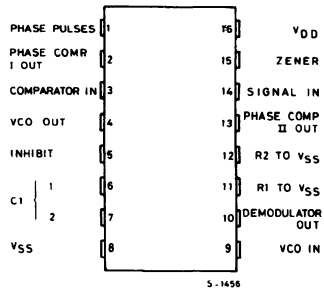
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- VERY LOW POWER CONSUMPTION : 100 μ W (TYP.) AT VCO $f_0 = 10\text{kHz}$, $V_{DD} = 5\text{V}$
- OPERATING FREQUENCY RANGE : UP TO 1.4MHz (TYP.) AT $V_{DD} = 10\text{V}$
- LOW FREQUENCY DRIFT : 0.06%/°C (typ.) AT $V_{DD} = 10\text{V}$
- CHOICE OF TWO PHASE COMPARATORS :
 - 1) EXCLUSIVE - OR NETWORK
 - 2) EDGE-CONTROLLED MEMORY NETWORK WITH PHASE-PULSE OUTPUT FOR LOCK INDICATION
- HIGH VCO LINEARITY : 1% (TYP.)
- VCO INHIBIT CONTROL FOR ON-OFF KEYING AND ULTRA-LOW STANDBY POWER CONSUMPTION
- SOURCE-FOLLOWER OUTPUT OF VCO CONTROL INPUT (demod. output)
- ZENER DIODE TO ASSIST SUPPLY REGULATION
- 5V, 10V AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4046B** (extended temperature range) and **HCF4046B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The **HCC/HCF4046B** COS/MOS Micropower Phase-Locked Loop (PLL) consists of a low-power, linear voltage-controlled oscillator (VCO) and two different phase comparators having a common signal-input amplifier and a common comparator input. A 5.2V zener diode is provided for supply regulation if necessary.



PIN CONNECTIONS



VCO Section

The VCO requires one external capacitor C1 and one or two external resistors (R1 or R1 and R2). Resistor R1 and capacitor C1 determine the frequency range of the VCO and resistor R2 enables the VCO to have a frequency offset if required. The high input impedance ($10^{12\Omega}$) of the VCO simplifies the design of low-pass filters by permitting the designer a wide choice of resistor-to-capacitor ratios. In order not to load the low-pass filter, a source-follower output of the VCO input voltage is provided at terminal 10 (DEMODULATED OUTPUT). If this terminal is used, a load resistor (R_S) of 10 k Ω or more should be connected from this terminal to V_{SS} . If unused this terminal should be left open. The VCO can be connected either directly or through frequency dividers to the comparator input of the phase comparators. A full COS/MOS logic swing is available at the output of the VCO and allows direct coupling to COS/MOS frequency dividers such as the **HCC/HCF4024B**, **HCC/HCF4018B**, **HCC/HCF4020B**, **HCC/HCF4022B**, **HCC/HCF4029B**, and **HBC/HBF4059A**. One or more **HCC/HCF4018B** (Presetable Divide-by-N Counter) or **HCC/HCF4029B** (Presetable Up/Down Counter), or **HBC/HBF4059A** (Programmable Divide-by-"N" Counter), together with the **HCC/HCF4046B** (Phase-Locked Loop) can be used to build a micropower low-frequency synthesizer. A logic 0 on the INHIBIT input "enables" the VCO and the source follower, while a logic 1 "turns off" both to minimize stand-by power consumption.

Phase Comparators

The phase-comparator signal input (terminal 14) can be direct-coupled provided the signal swing is within COS/MOS logic levels [logic "0" $\leq 30\%$ ($V_{DD} - V_{SS}$), logic "1" $\geq 70\%$ ($V_{DD} - V_{SS}$)]. For smaller swings the signal must be capacitively coupled to the self-biasing amplifier at the signal input. Phase comparator I is an exclusive-OR network ; it operates analogously to an over-driven balanced mixer. To maximize the lock range, the signal- and comparator-input frequencies must have a 50% duty cycle. With no signal or noise on the signal input, this phase comparator has an average output voltage equal to $V_{DD}/2$. The low-pass filter connected to the output of phase comparator I supplies the averaged voltage to the VCO input, and causes the VCO to oscillate at the center frequency (f_0). The frequency range of input signals on which the PLL will lock if it was initially out of lock is defined as the frequency capture range ($2f_c$). The frequency range of input signals on which the loop will stay locked if it was initially in lock is defined as the frequency lock range ($2f_L$). The capture range is \leq the

lock range. With phase comparator I the range of frequencies over which the PLL can acquire lock (capture range) is dependent on the low-pass-filter characteristics, and can be made as large as the lock range. Phase-comparator I enables a PLL system to remain in lock in spite of high amounts of noise in the input signal. One characteristic of this type of phase comparator is that it may lock onto input frequencies that are close to harmonics of the VCO center-frequency. A second characteristic is that the phase angle between the signal and the comparator input varies between 0° and 180° , and is 90° at the center frequency. Fig. (a) shows the typical, triangular, phase-to-output response characteristic of phase-comparator I. Typical waveforms for a COS/MOS phase-locked-loop employing phase comparator I in locked condition of f_0 is shown in fig. (b). Phase-comparator II is an edge-controlled digital memory network. It consists of four flip-flop stages, control gating, and a three-stage output-circuit comprising p- and n-type drivers having a common output node. When the p-MOS or n-MOS drivers are ON they pull the output up to V_{DD} or down to V_{SS} , respectively. This type of phase comparator acts only on the positive edges of the signal and comparator inputs. The duty cycles of the signal and comparator inputs are not important since positive transitions control the PLL system utilizing this type of comparator. If the signal-input frequency is higher than the comparator-input frequency, the p-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal-input frequency is lower than the comparator-input frequency, the n-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal and comparator-input frequencies are the same, but the signal input lags the comparator input in phase, the n-type output driver is maintained ON for a time corresponding to the phase difference. If the signal and comparator-input frequencies are the same, but the comparator input lags the signal in phase, the p-type output driver is maintained ON for a time corresponding to the phase difference. Subsequently, the capacitor voltage of the low-pass filter connected to this phase comparator is adjusted until the signal and comparator inputs are equal in both phase and frequency. At this stable point both p- and n-type output drivers remain OFF and thus the phase comparator output becomes an open circuit and holds the voltage on the capacitor of the low-pass filter constant. Moreover the signal at the "phase pulses" output is a high level which can be used for indicating a locked condition. Thus, for phase comparator II, no phase difference exists be-

tween signal and comparator input over the full VCO frequency range. Moreover, the power dissipation due to the low-pass filter is reduced when this type of phase comparator is used because both the p- and n-type output drivers are OFF for most of the signal input cycle. It should be noted that the PLL

lock range for this type of phase comparator is equal to the capture range, independent of the low-pass filter. With no signal present at the signal input, the VCO is adjusted to its lowest frequency for phase comparator II. Fig. (c) shows typical waveforms for a COS/MOS PLL employing phase comparator II in

Figure a : Phase-Comparator I Characteristics at Low-Pass Filter Output.

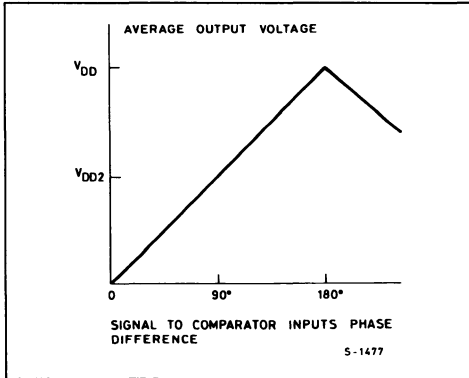


Figure b : Typical Waveforms for COS/MOS Phase Locked-Loop Employing Phase Comparator I in Locked Condition of f_0 .

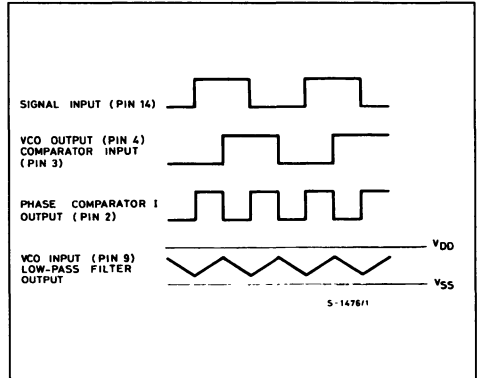
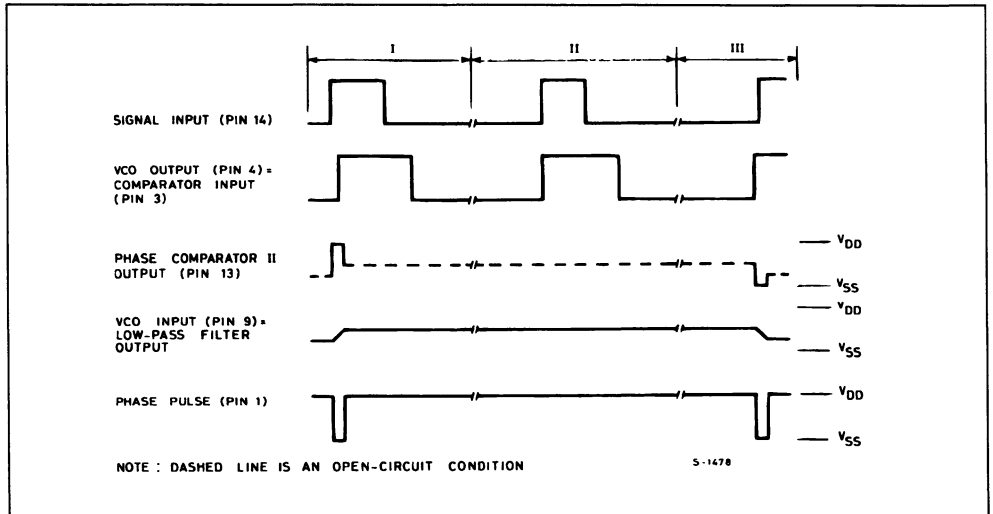
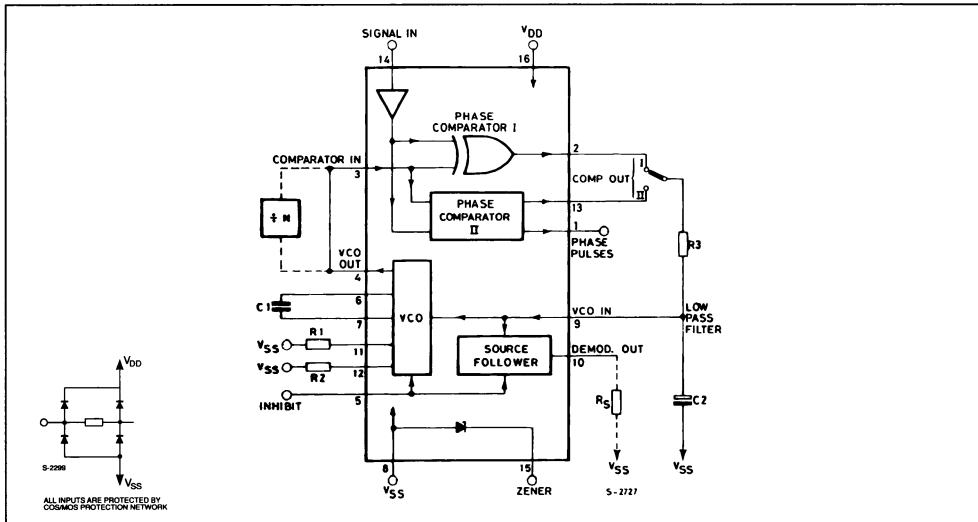


Figure C : Typical Waveforms For COS/MOS Phase-locked Loop Employing Phase Comparator II In Locked Condition.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
VCO SECTION														
V _{OH}	Output High Voltage	0/ 5 0/10 0/15		< 1 < 1 < 1	5 10 15	4.95 9.95 14.95		4.95 9.95 14.95	5 10 15		4.95 9.95 14.95		V	
V _{OL}	Output Low Voltage	5/0 10/0 15/0		< 1 < 1 < 1	5 10 15		0.05 0.05 0.05			0.05 0.05 0.05	0.05 0.05 0.05			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1		
PHASE COMPARATOR SECTION														
I _{DD}	Total Device Current Pin 14 = Open Pin 5 = V _{DD}	0/ 5			5		0.1		0.05	0.1		0.1	mA	
		0/10			10		0.5		0.25	0.5		0.5		
		0/15			15		1.5		0.75	1.5		1.5		
		0/20			20		4		2	4		4		
	Pin 14 = V _{SS} or V _{DD} Pin 5 = V _{DD}	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		HCF Types	0/20			20		100		0.08	100		3000	
			0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15			15		80		0.04	80		600				
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5	1.5	V		
			9/1	< 1	10		3			3	3			
			13.5/1.5	< 1	15		4			4	4			
I _{IH} , I _{IL}	Input Leakage Current (except. pin 14)	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15			15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1		
I _{OUT}	3-state Leakage Current	HCC Types	0/18	0/18		18		± 0.4	$\pm 10^{-4}$	± 0.4		± 12	μ A	
		HCF Types	0/15	0/15		15		± 1.0	$\pm 10^{-4}$	± 1.0		± 7.5		
C _I	Input Capacitance			Any Input					5	7.5		pF		

* T_{Low} = -55°C for HCC device : -40°C for HCF device.* T_{High} = +125°C for HCC device : +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C)

Symbol	Parameter	Test Conditions	Value			Unit		
			V _{DD} (V)	Min.	Typ.		Max.	
VCO SECTION								
P _D	Operating Power Dissipation	fo = 10 KHz R1 = 10 MΩ R2 = ∞ V _{COIN} = $\frac{V_{DD}}{2}$	5		70	140	μW	
			10		800	1600		
			15		3000	6000		
f _{max}	Maximum Frequency	R1 = 10 KΩ C1 = 50 pF R2 = ∞ V _{COIN} = V _{DD}	5	0.3	0.6		MHz	
			10	0.6	1.2			
			15	0.8	1.6			
		R1 = 5 KΩ n C1 = 50 pF R2 = ∞ V _{COIN} = V _{DD}	5	0.5	0.8			
			10	1	1.4			
15	1.4	2.4						
	Center Frequency (f ₀) and Frequency Range f _{max} - f _{min}	Programmable with external components R1, R2 and C1						
Linearity		V _{COIN} =2.5V ± 0.3 R1=10 KΩ V _{COIN} =5V ± 1 R1=100 KΩ V _{COIN} =5V ± 2.5 R1=400 KΩ V _{COIN} =7.5V ± 1.5 R1=100 KΩ V _{COIN} =7.5V ± 5 R1=1 MΩ	5		1.7		%	
			10		0.5			
			10		4			
			15		0.5			
			15		7			
Temperature Frequency Stability (no frequency offset) f _{min} = 0	Temperature Frequency Stability (no frequency offset) f _{min} = 0		5		±0.12		%°C	
			10		±0.04			
			15		±0.015			
	Temperature Frequency Stability (frequency offset) f _{min} ≠ 0		5		±0.09			
			10		±0.07			
			15		±0.03			
V _{CO}	Output Duty Cycle		5, 10, 15		50		%	
t _{THL} t _{TLH}	VCO Output Transition Time		5		100	200	ns	
			10		50	100		
			15		40	80		
	Source Follower Output (demodulated Output): Off-set Voltage V _{COIN} - V _{DEM}	R _S > 10 KΩ	5, 10, 15		1.8	2.5	V	
	Source Follower Output (demodulated Output): Linearity	R _S =100 KΩ V _{COIN} =2.5 ^{+0.30} 3V	5		0.3		%	
		R _S =300 KΩ V _{COIN} =5 ^{+2.5} 5V	10		0.7			
		R _S =500 KΩ V _{COIN} =7.5 ⁺⁵ 5V	15		0.9			
V _Z	Zener Diode Voltage	I _Z = 50 μA		4.45	5.5	7.5	V	
R _Z	Zener Dynamic Resistance	I _Z = 1 mA			40		Ω	
PHASE COMPARATOR SECTION								
R14	Pin 14 (signal in) Input Resistance		5	1	2		MΩ	
			10	0.2	0.4			
			15	0.1	0.2			
	A.C. Coupled Signal Input Voltage Sensitivity * (peak to peak)		f _{in} = 100 KHz sine wave	5	180	360		mV
				10	330	660		
		15	900	1800				

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
PHASE COMPARATOR SECTION (cont'd)							
T _{PHL}	Propagation Delay Time High to Low Level Pins 14 to 13		5	225	450		ns
			10	100	200		
			15	65	130		
T _{PLH}	Propagation Delay Time Low to High, Level		5		350	700	ns
			10		150	300	
			15		100	200	
T _{PHZ}	Propagation Delay Time 3-state High Level to High Impedance Pins 14 to 13		5		225	450	ns
			10		100	200	
			15		65	130	
T _{PLZ}	Low Level to High Impedance		5		285	570	ns
			10		130	260	
			15		95	190	
t _r , t _f	Input Rise or Fall Time Comparator Pin 3		5			50	μs
			10			1	
			15			0.3	
	Signal Pin 14		5			500	μs
			10			20	
			15			2.5	
T _{THL} , T _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

* For sine wave the frequency must be greater than 10KHz for Phase Comparator II.

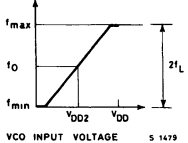
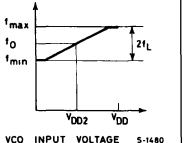
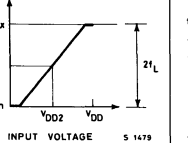
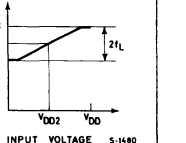
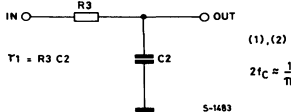
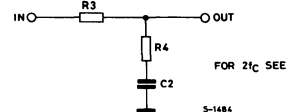
DESIGN INFORMATION

This information is a guide for approximating the values of external components for the **HCC/HCF 4046B** in a Phase-Locked-Loop system. The selected external components must be within the following ranges :

$5k\Omega \leq R1, R2, R_S \leq 1M\Omega$

$C1 \geq 100pF$ at $V_{DD} \geq 5V$

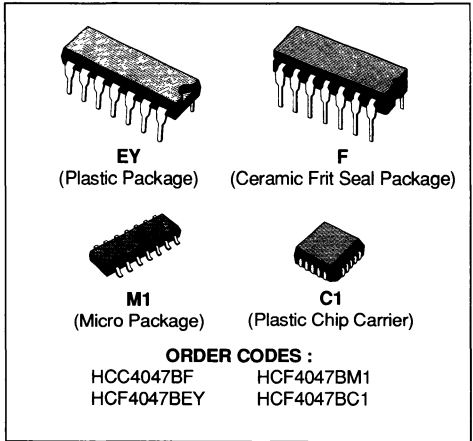
$C1 \geq 50pF$ at $V_{DD} \geq 10V$

CHARACTERISTICS	USING PHASE COMPARATOR I		USING PHASE COMPARATOR II	
	VCO WITHOUT OFFSET $R2 = \infty$	VCO WITH OFFSET	VCO WITHOUT OFFSET $R2 = \infty$	VCO WITH OFFSET
VCO Frequency				
For No Signal Input	VCO in PLL System will Adjust to centre frequency f_0		VCO in PLL System will Adjust to Lowest Operating Frequency f_{min}	
Frequency Lock Range, $2f_L$	$2f_L = \text{full VCO frequency range}$ $2f_L = f_{max} - f_{min}$			
Frequency Capture Range, $2f_c$	 <p>(1), (2) $2f_c \approx \frac{1}{\pi} \sqrt{\frac{2\pi f_L}{T_1}}$ S-1483</p>		$f_c = f_L$	
Loop Filter Component Selection	 <p>FOR $2f_c$ SEE REF (2) S-1484</p>			
Phase Angle Between Signal and Comparator	90° at Centre Frequency (f_0), approximating 0° and 180° at ends of lock range ($2f_L$)		Always 0° in lock	
Locks on Harmonics of Centre Frequency	Yes		No	
Signal Input Noise Rejection	High		Low	

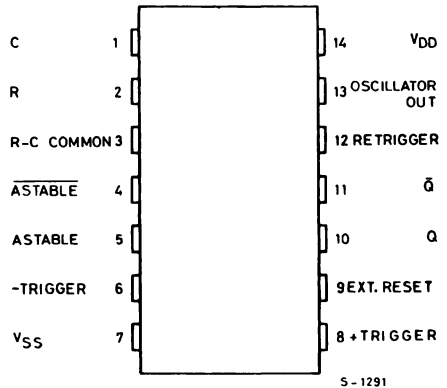
* G.S. Moskytz "miniaturized RC filters using phase Lockedloop" BSTJ, may 1965

LOW-POWER MONOSTABLE/ASTABLE MULTIVIBRATOR

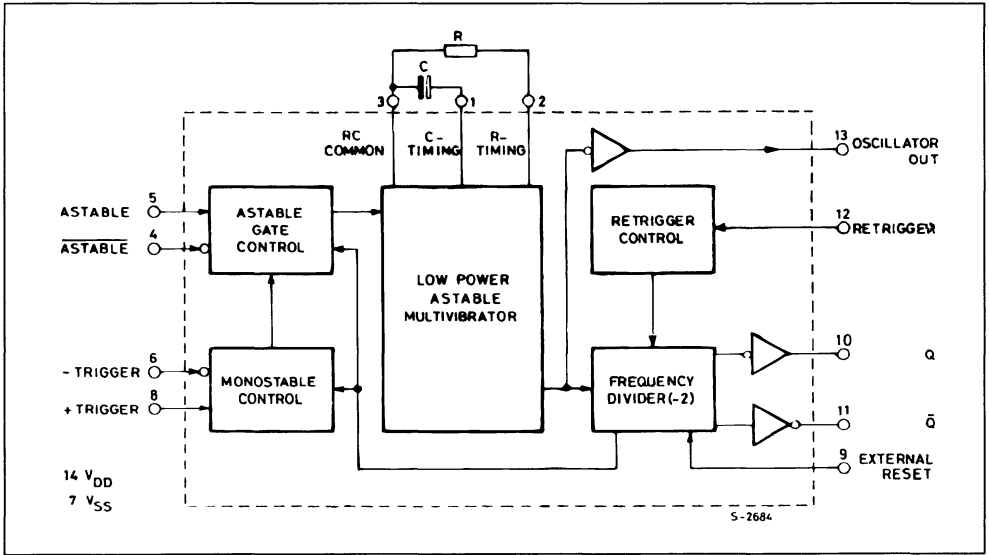
- LOW POWER CONSUMPTION : SPECIAL COS/MOS OSCILLATOR CONFIGURATION
- MONOSTABLE (one-shot) OR ASTABLE (free-running) OPERATION
- TRUE AND COMPLEMENTED BUFFERED OUTPUTS
- ONLY ONE EXTERNAL R AND C REQUIRED
- BUFFERED INPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

The **HCC4047B** (extended temperature range) and **HCF4047B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4047B** consists of a gateable astable multivibrator with logic techniques incorporated to permit positive or negative edge-triggered monostable multivibrator action with retriggering and external counting options. Inputs include +TRIGGER -TRIGGER, ASTABLE, ASTABLE, RETRIGGER, and EXTERNAL RESET. Buffered outputs are Q, \bar{Q} , and OSCILLATOR. In all modes of operation, an external capacitor must be connected between C-Timing and RC-Common terminals, and an external resistor must be connected between the R-Timing and RC-Common terminals. For operating modes see functional terminal connections and application notes.

PIN CONNECTIONS


BLOCK DIAGRAM



FUNCTIONAL TERMINAL CONNECTIONS

Function*	Terminal Connections			Output Pulse From	Output Period or Pulse Width
	to V _{DD}	to V _{SS}	Input Pulse to		
Astable Multivibrator :					
Free Running	4, 5, 6, 14	7, 8, 9, 12	-	10, 11, 13	$t_A(10, 11) = 4.40RC$
True Gating	4, 6, 14	7, 8, 9, 12	5	10, 11, 13	
Complement Gating	6, 14	5, 7, 8, 9, 12	4	10, 11, 13	$t_A(13) = 2.20RC$
Monostable Multivibrator :					
Positive-Edge Trigger	4, 14	5, 6, 7, 9, 12	8	10, 11	
Negative-Edge Trigger	4, 8, 14	5, 7, 9, 12	6	10, 11	
Retriggerable	4, 14	5, 6, 7, 9	8, 12	10, 11	
External Countdown**	14	5, 6, 7, 8, 9, 12	-	10, 11	$t_M(10, 11) = 2.48RC$

* In all cases external capacitor and resistor between pins, 1, 2 and 3 (see logic diagrams).

** Input pulse to Reset of External Counting Chip.
External Counting Chip Output to pin 4

ABSOLUTE MAXIMUM RATINGS

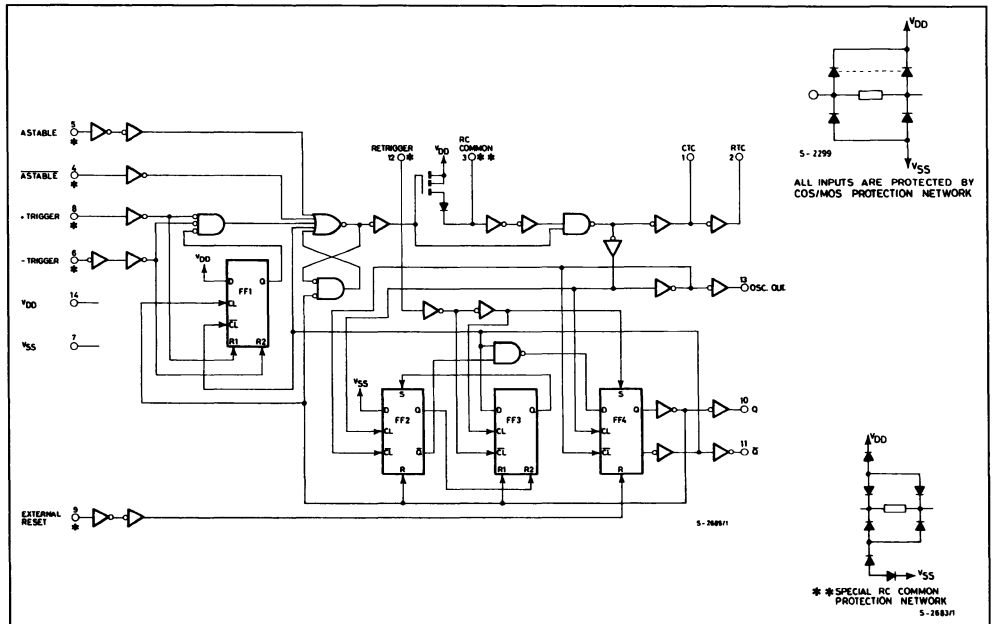
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltage values are referred to V_{SS} pin voltage.

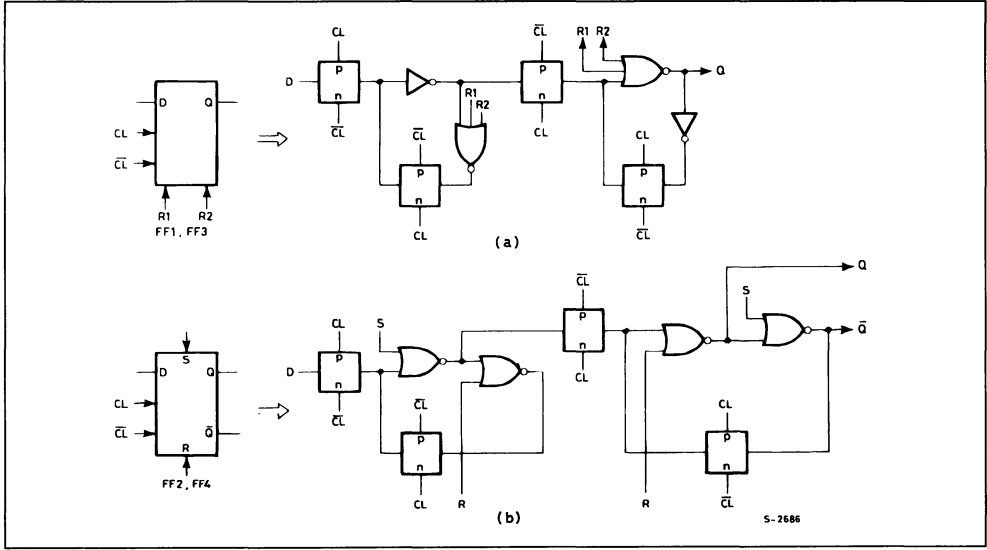
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



Detail for Flip-flops FF1 and FF3 (a) and for Flip-flops FF2 and FF4 (b).



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1	0.02	1		30	μA
			0/10			10		2	0.02	2		60	
			0/15			15		4	0.02	4		120	
		HCF Types	0/5			5		4	0.02	4		30	
			0/10			10		8	0.02	8		60	
			0/15			15		16	0.02	16		120	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95		V	
		0/10	< 1	10	9.95		9.95			9.95			
		0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V	
		10/0	< 1	10		0.05			0.05		0.05		
		15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V	
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.

* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit			
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *				
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.		
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5				1.5		1.5	V		
			9/1	< 1	10		3				3		3			
			13.5/1.5	< 1	15		4				4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5	5	-2		-1.6	-3.2		-1.15			mA		
			0/5	4.6	5	-0.64		-0.51	-1		-0.36					
			0/10	9.5	10	-1.6		-1.3	-2.6		-0.9					
			0/15	13.5	15	-4.2		-3.4	-6.8		-2.4					
		HCF Types	0/5	2.5	5	-1.53		-1.36	-3.2		-1.1					
			0/5	4.6	5	-0.52		-0.44	-1		-0.36					
			0/10	9.5	10	-1.3		-1.1	-2.6		-0.9					
			0/15	13.5	15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4	5	0.64		0.51	1		0.36			mA		
			0/10	0.5	10	1.6		1.3	2.6		0.9					
			0/15	1.5	15	4.2		3.4	6.8		2.4					
		HCF Types	0/5	0.4	5	0.52		0.44	1		0.36					
			0/10	0.5	10	1.3		1.1	2.6		0.9					
			0/15	1.5	15	3.6		3.0	6.8		2.4					
		I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1			± 1	μ A
				HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3			± 1	
C _I	Input Capacitance			Any Input					5	7.5			pF			

* T_{Low} = -55°C for HCC device : -40°C for HCF device.* T_{High} = +125°C for HCC device : +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

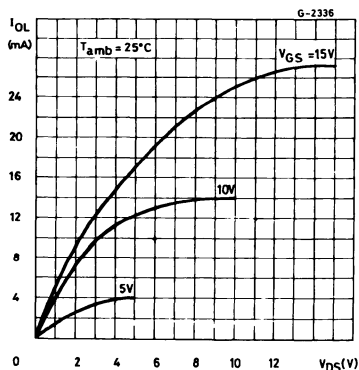
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

Symbol	Parameter		Test Conditions		Value			Unit
				V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time	Astable, Astable to osc. out		5		200	400	ns
				10		100	200	
				15		80	160	
		Astable, Astable to Q, Q		5		350	700	
				10		175	350	
				15		125	250	
		+ or - Trigger to Q, Q		5		500	1000	
				10		225	450	
				15		150	300	

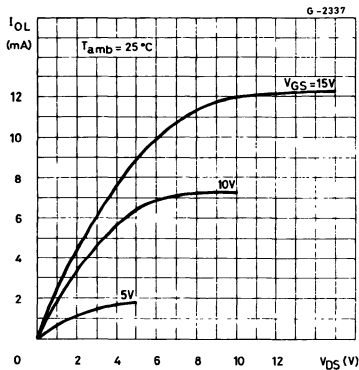
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.		
t _{PLH} , t _{PHL}	Propagation Delay Time	Retrigger to Q, \bar{Q}	5		300	600	ns	
			10		150	300		
			15		100	200		
		External Reset to Q, \bar{Q}	5		250	500		
			10		100	200		
			15		70	140		
t _{rHL} , t _{TLH}	Transition Time Osc. Out Q, \bar{Q}		5		100	200		
			10		50	100		
			15		40	80		
t _w	Input Pulse Width :	+ Trigger, - Trigger	5		200	400		
			10		80	160		
			15		50	100		
		Reset	5		100	200		
			10		50	100		
			15		30	60		
		Retrigger	5		300	600		
			10		115	230		
			15		75	150		
t _r , t _f	Input Rise and Fall Time All Inputs		5	Unlimited		μs		
			10					
			15					
	Q or \bar{Q} Deviation from 50% Duty Factor		5	± 0.5	± 1	%		
			10	± 0.5	± 1			
			15	± 0.1	± 0.5			

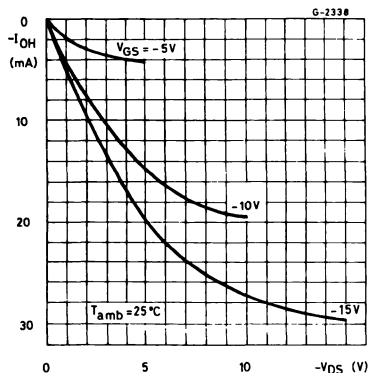
Typical Output Low (sink) Current Characteristics.



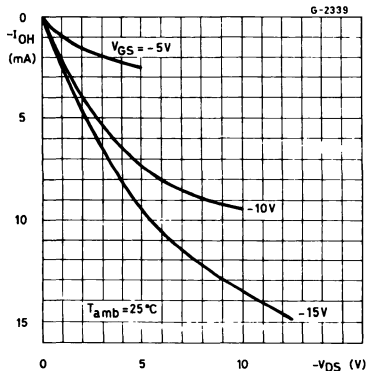
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.



Minimum Output High (source) Current Characteristics.



APPLICATION INFORMATION

1 - CIRCUIT DESCRIPTION

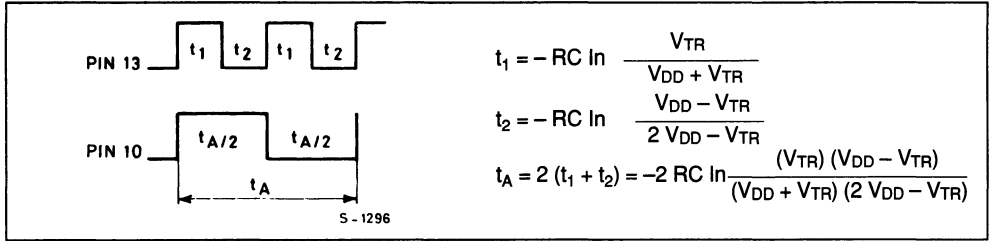
Astable operation is enabled by a high level on the ASTABLE input. The period of the square wave at the Q and Q Outputs in this mode of operation is a function of the external components employed. "True" input pulses on the ASTABLE input or "Complement" pulses on the ASTABLE input allow the circuit to be used as a gatable multivibrator. The OSCILLATOR output period will be half of the Q terminal output in the astable mode. However, a 50% duty cycle is not guaranteed at this output. In the monostable mode, positive-edge triggering is accomplished by application of a leading-edge pulse to the +TRIGGER input and a low level to the -TRIGGER input. For negative-edge triggering, a trailing-edge pulse is applied to the -TRIGGER and a high level is applied to the +TRIGGER. Input pulses may be of any duration relative to the output pulse. The multivibrator can be retriggered (on the leading edge only) by applying a common pulse to both the RETRIGGER and +TRIGGER inputs. In this mode

the output pulse remains high as long as the input pulse period is shorter than the period determined by the RC components. An external countdown option can be implemented by coupling "Q" to an external "N" counter and resetting the counter with the trigger pulse. The counter output pulse is fed back to the ASTABLE input and has a duration equal to N times the period of the multivibrator. A high level on the EXTERNAL RESET input assures no output pulse during an "ON" power condition. This input can also be activated to terminate the output pulse at any time. In the monostable mode, a high-level or power-on reset pulse, must be applied to the EXTERNAL RESET whenever V_{DD} is applied.

2 - ASTABLE MODE

The following analysis presents worst-case variations from unit-to-unit as a function of transfer-voltage (V_{TR}) shift (33% – 67% V_{DD}) for free-running (astable) operation.

ASTABLE MODE WAVEFORMS.



Typ : $V_{TR} = 0.5 V_{DD}$ $t_A = 4.40 RC$

Min : $V_{TR} = 0.33 V_{DD}$ $t_A = 4.62 RC$

Max : $V_{TR} = 0.67 V_{DD}$ $t_A = 4.62 RC$

thus if $t_A = 4.40 RC$ is used, the maximum variation will be (+ 5.0%, - 0.0%)

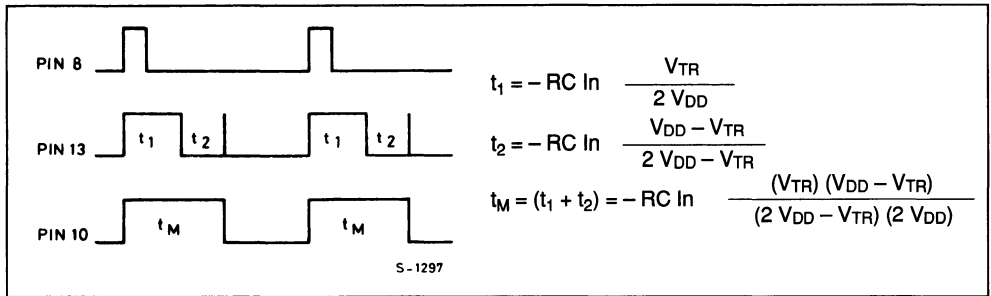
In addition to variations from unit-to-unit, the astable

period may vary as a function of frequency with respect to V_{DD} and temperature.

3 - MONOSTABLE MODE

The following analysis presents worst-case variations from unit-to-unit as a function of transfer-voltage (V_{TR}) shift (33% - 67% V_{DD}) for one-shot (monostable) operation.

MONOSTABLE WAVEFORMS.



Where t_M = monostable mode pulse width. Values for t_M are as follows :

Typ : $V_{TR} = 0.5 V_{DD}$ $t_M = 2.48 RC$

Min : $V_{TR} = 0.33 V_{DD}$ $t_M = 2.71 RC$

Max : $V_{TR} = 0.67 V_{DD}$ $t_M = 2.48 RC$

Thus if $t_M = 2.48 RC$ is used, the maximum variation will be (+ 9.3%, - 0.0%).

Note : In the astable mode, the first positive half cycle has a duration of T_M ; succeeding durations are $t_A/2$.

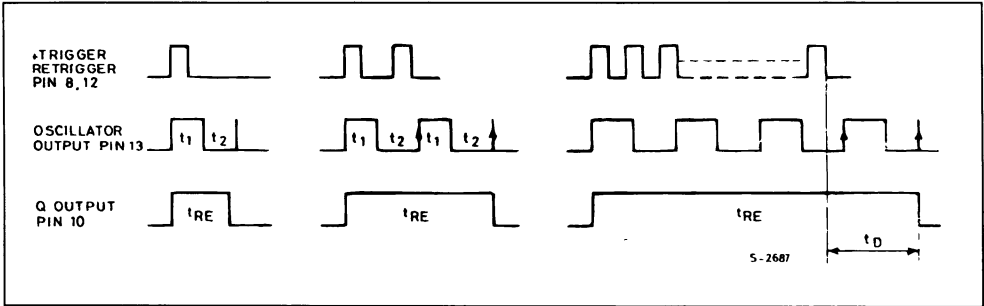
In addition to variations from unit to unit, the monostable pulse width may vary as a function of frequency with respect to V_{DD} and temperature.

mode to extend the output-pulse duration, or to compare the frequency of an input signal with that of the internal oscillator. In the retrigger mode the input pulse is applied to terminals 8 and 12, and the output is taken from terminal 10 or 11. As shown in fig. A normal monostable action is obtained when one retrigger pulse is applied. Extended pulse duration is obtained when more than one pulse is applied. For two input pulses, $t_{RE} = t_1' + t_1 + 2t_2$. For more than two pulses, t_{RE} (Q OUTPUT) terminates at some variable time t_D after the termination of the last retrigger pulse. t_D is variable because t_{RE} (Q OUTPUT) terminates after the second positive edge of the oscillator output appears at flip-flop 4 (see logic diagram).

4 - RETRIGGER MODE

The HCC/HCF4047B can be used in the retrigger

Figure A : Retrigger-mode Waveforms.



5 - EXTERNAL COUNTER OPTION

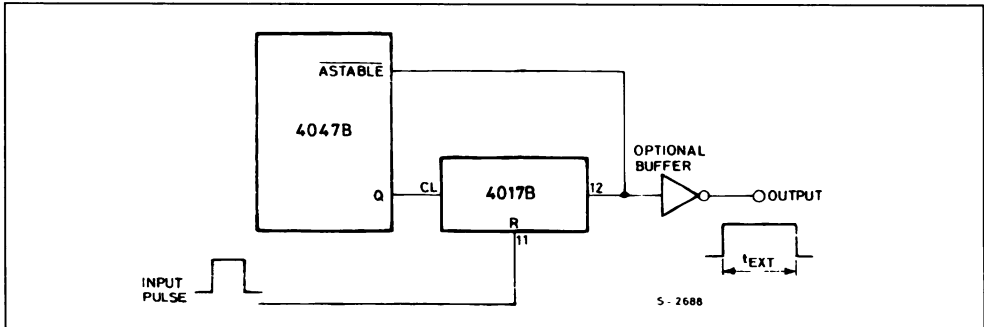
Time t_M can be extended by any amount with the use of external counting circuitry. Advantages include digitally controlled pulse duration, small timing capacitors for long time periods, and extremely fast recovery time.

A typical implementation is shown in fig. B. The pulse duration at the output is

$$t_{ext} = (N - 1) (t_A) + (t_M + t_A/2)$$

Where t_{ext} = pulse duration of the circuitry, and N is the number of counts used.

Figure B : Implementation of External Counter Option.



6 - POWER CONSUMPTION

In the standby mode (Monostable or Astable), power dissipation will be a function of leakage current in the circuit, as shown in the static electrical characteristics. For dynamic operation, the power needed to charge the external timing capacitor C is given by the following formula :

Astable Mode : $P = 2CV^2f$. (Output at Pin 13)
 $P = 4CV^2f$. (Output at Pin 10 and 11)

Monostable Mode : $P = \frac{(2.9CV^2) (Duty Cycle)}{T}$

(Output at Pin 10 and 11)

The circuit is designed so that most of the total power is consumed in the external components. In practice, the lower the values of frequency and volt-

age used, the closer the actual power dissipation will be to the calculated value.

Because the power dissipation does not depend on R, a design for minimum power dissipation would be a small value of C. The value of R would depend on the desired period (within the limitations discussed above).

7 - TIMING-COMPONENT LIMITATIONS

The capacitor used in the circuit should be non-polarized and have low leakage (i.e. the parallel resistance of the capacitor should be an order of magnitude greater than the external resistor used). There is no upper or lower limit for either R or C value to maintain oscillation.

However, in consideration of accuracy, C must be much larger than the inherent stray capacitance in

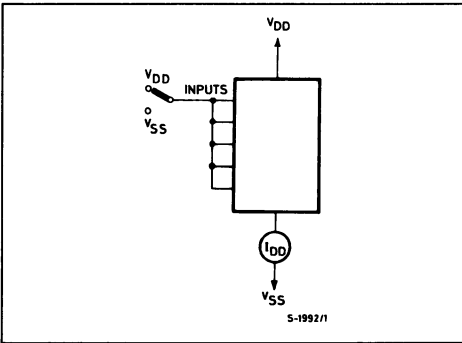
the system (unless this capacitance can be measured and taken into account). R must be much larger than the COS/MOS "ON" resistance in series with it, which typically is hundreds of ohms. In addition, with very large values of R, some short-term instability with respect to time may be noted.

The recommended values for these components to maintain agreement with previously calculated formulas without trimming should be :

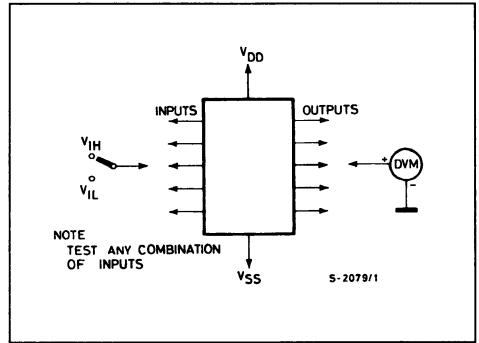
- $C \geq 100\text{pF}$, up to any practical value, for astable modes ;
- $C \geq 1000\text{pF}$, up to any practical value, for monostable modes.
- $10\text{K}\Omega \leq R \leq 1\text{M}\Omega$.

TEST CIRCUITS

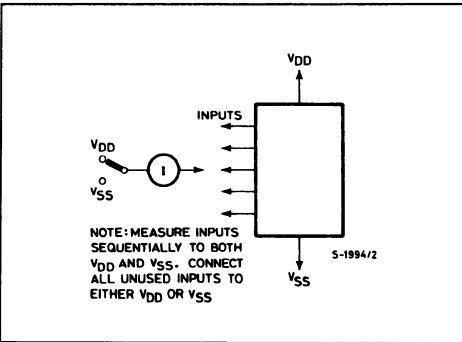
Quiescent Device Current.



Input Voltage.



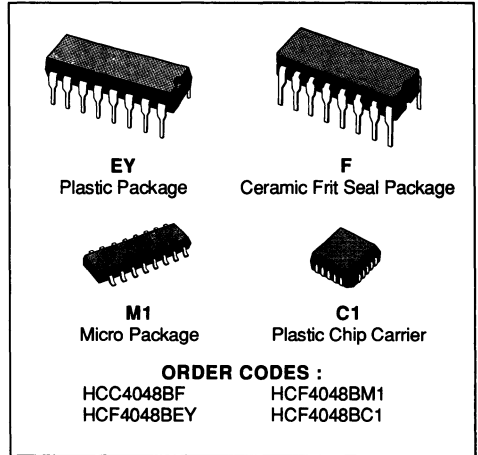
Input Current.





MULTIFUNCTION EXPANDABLE 8-INPUT GATE

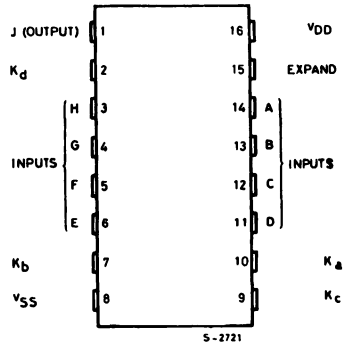
- THREE-STATE OUTPUT
- MANY LOGIC FUNCTIONS AVAILABLE IN ONE PACKAGE
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



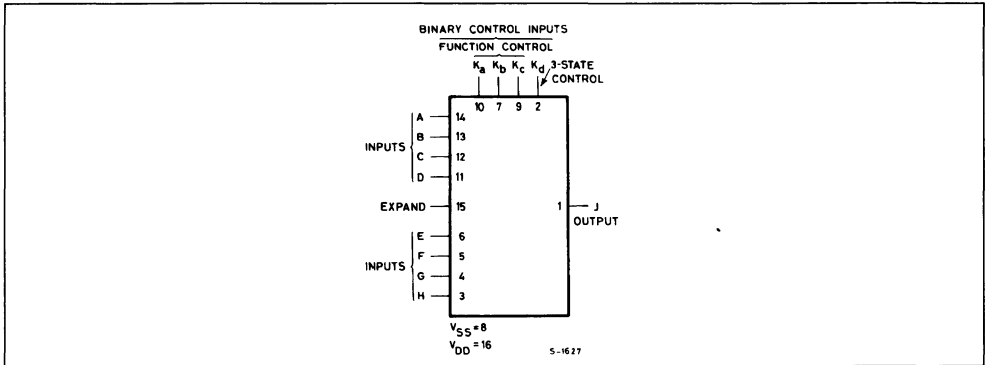
DESCRIPTION

The **HCC4048B** (extended temperature range) and **HCF4048B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4048B** is an 8-input gate having four control inputs. Three binary control inputs - Ka, Kb, and Kc - provide the implementation of eight different logic functions. These functions are OR, NOR, AND, NAND, OR/AND, OR/NAND, AND/OR and AND/NOR. A fourth control input-Kd provides the user with a 3-state output. When control input Kd is high the output is either a logic 1 or a logic 0 depending on the inner states. When control input Kd is low, the output is an open circuit. This feature enables the user to connect this device to a common bus line. In addition to the eight input lines, an EXPAND input is provided that permits the user to increase the number of inputs to one **HCC/HCF4048B**. For example, two **HCC/HCF4048B**'s can be cascaded to provide a 16-input multifunction gate. When the EXPAND input is not used, it should be connected to Vss.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

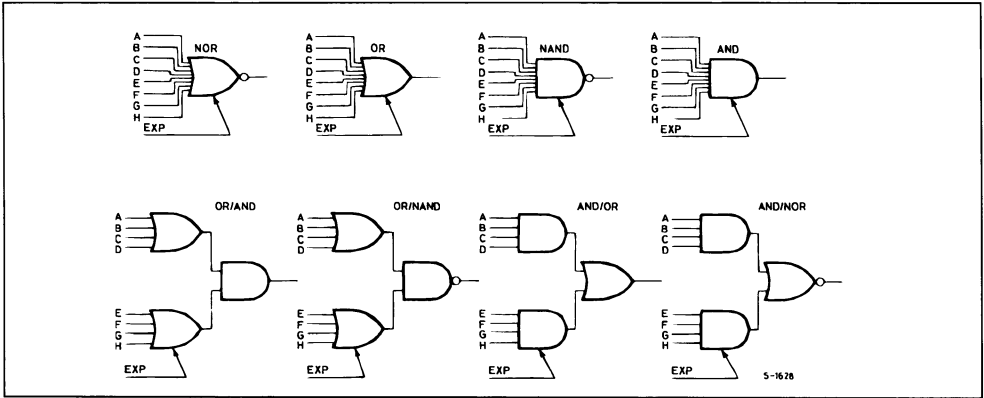
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltages values are referred to V_{SS} pin voltage.

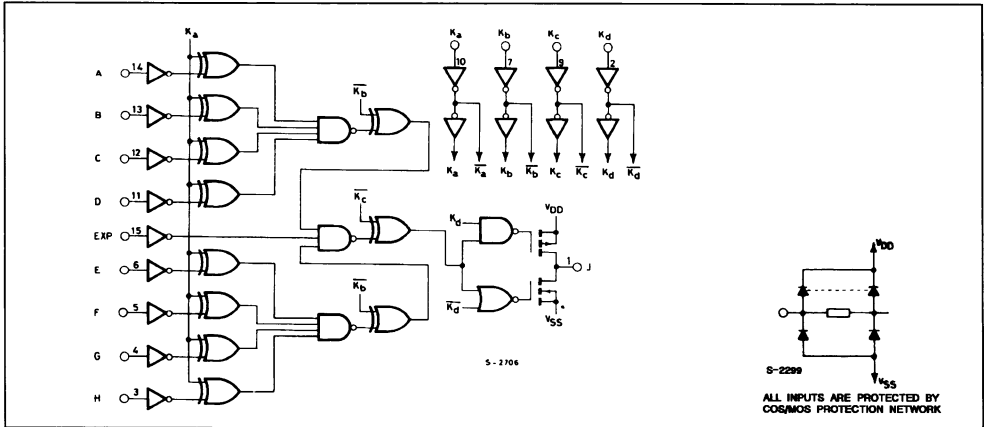
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

BASIC LOGIC CONFIGURATIONS



LOGIC DIAGRAM



FUNCTION TRUTH TABLE

Output Function	Boolean Expression	K _a	K _b	K _c	Unused Input
NOR	$J = A + B + C + D + E + F + G + H$	0	0	0	V _{SS}
OR	$J = A + B + C + D + E + F + G + H$	0	0	1	V _{SS}
OR/AND	$J = (A + B + C + D) \cdot (E + F + G + H)$	0	1	0	V _{SS}
OR/NAND	$J = (A + B + C + D) \cdot (E + F + G + H)$	0	1	1	V _{SS}
AND	$J = ABCDEFGH$	1	0	0	V _{DD}
NAND	$J = \overline{ABCDEFGH}$	1	0	1	V _{DD}
AND/NOR	$J = \overline{ABCD + EFGH}$	1	1	0	V _{DD}
AND/OR	$J = \overline{ABCD + EFGH}$	1	1	1	V _{DD}

K_d = 1 Normal Inverter Action
 K_d = 0 High Impedance Output

EXPAND Input = 0

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
		0/20			20		5		0.02	5		150		
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
0/15				15		4		0.01	4		30			
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V		
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5			3.5		V		
		1/9	< 1	10	7		7			7				
		1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5			1.5		1.5	V		
		9/1	< 1	10		3			3		3			
		13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2	-1.6	-3.2		-1.15	mA		
			0/5	4.6		5	-0.64	-0.51	-1		-0.36			
			0/10	9.5		10	-1.6	-1.3	-2.6		-0.9			
		0/15	13.5		15	-4.2	-3.4	-6.8		-2.4				
		HCF Types	0/5	2.5		5	-1.53	-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52	-0.44	-1		-0.36			
0/10	9.5			10	-1.3	-1.1	-2.6		-0.9					
0/15	13.5		15	-3.6	-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64	0.51	1		0.36	mA		
			0/10	0.5		10	1.6	1.3	2.6		0.9			
			0/15	1.5		15	4.2	3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52	0.44	1		0.36			
			0/10	0.5		10	1.3	1.1	2.6		0.9			
			0/15	1.5		15	3.6	3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.01		± 1	μ A	
		HCF Types	0/15											15
I _{OH}	3-state Output Current	HCC Types	0/18	0/18		18		± 0.4	$\pm 10^{-4}$	± 0.4		± 12	μ A	
		HCF Types	0/15	0/15		15		± 1.0	$\pm 10^{-4}$	± 1.0		± 7.5		
C _I	Input Capacitance		Any Input					5	7.5			pF		

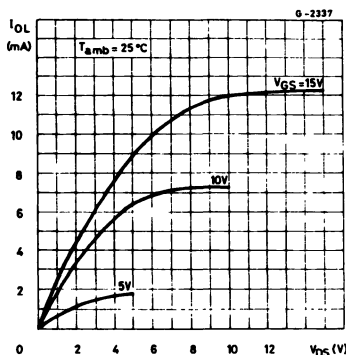
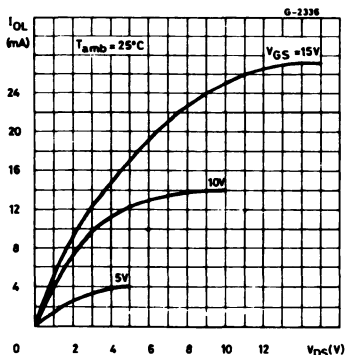
* T_{LOW} = -55°C for HCC device : -40°C for HCF device.* T_{HIGH} = -125°C for HCC device : -85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V,

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

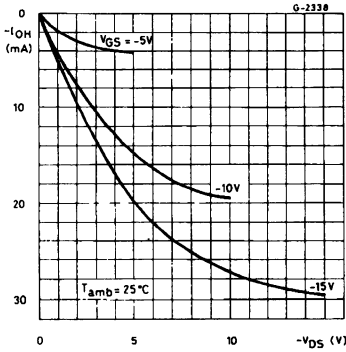
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time Inputs to Output and Ka to Output		5		300	600	ns
			10		150	300	
			15		120	240	
	Kb to Output		5		225	450	
			10		85	170	
			15		55	110	
	Kc to Output		5		140	280	
			10		50	100	
			15		40	80	
	Expand Input to Output		5		190	380	
			10		90	180	
			15		65	130	
t_{PHZ} , t_{PLZ} t_{PZH} , t_{PZL}	3-state Propagation Delay Time Kd to Output	$R_L = 1\text{k}\Omega$	5		80	160	
			10		35	70	
			15		25	50	
t_{THL} , t_{TLH}	Transition Time		5		100	200	
			10		50	100	
			15		40	80	
3-state Output Capacitance					5	10	pF

Typical Output Low (sink) Current Characteristics.

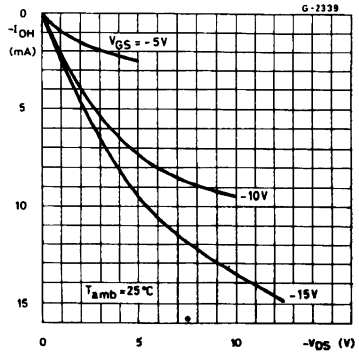
Minimum Output Low (sink) Current Characteristics.



Typical Output High (source) Current Characteristics.

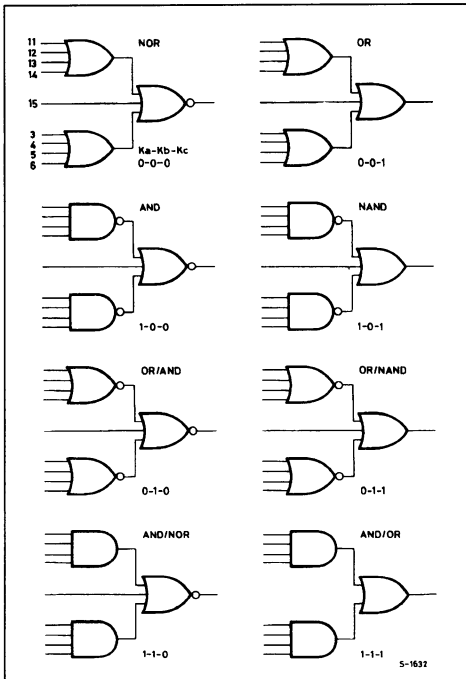


Minimum Output high (source) Current Characteristics.



APPLICATIONS OF EXPAND INPUT

ACTUAL-CIRCUIT LOGIC CONFIGURATIONS



EXPANSION LOGIC AND TRUTH TABLE

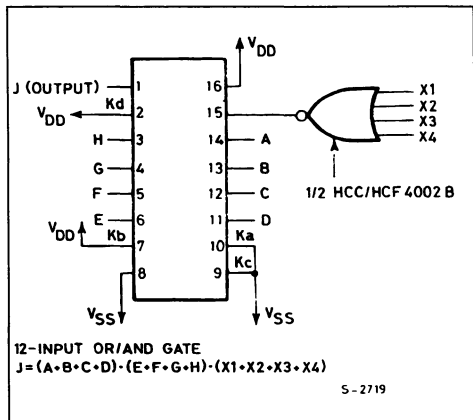
IMPLEMENTATION OF EXPAND INPUT FOR 9 OR MORE INPUTS

OUTPUT FUNCTION	FUNCTION NEEDED AT EXPAND INPUT	OUTPUT BOOLEAN EXPRESSION
NOR	OR	$J = \overline{(A+B+C+D+E+F+G+H) + (EXP)}$
OR	OR	$J = (A+B+C+D+E+F+G+H) + (EXP)$
AND	NAND	$J = \overline{(ABCDEFHG)} (EXP)$
NAND	NAND	$J = \overline{(ABCDEFHG)} (EXP)$
OR/AND	NOR	$J = \overline{(A+B+C+D)} (E+F+G+H) (EXP)$
OR/NAND	NOR	$J = \overline{(A+B+C+D)} \cdot \overline{(E+F+G+H)} (EXP)$
AND/NOR	AND	$J = \overline{(ABCD)} + \overline{(EFGH)} + (EXP)$
AND/OR	AND	$J = \overline{(ABCD)} + \overline{(EFGH)} + (EXP)$

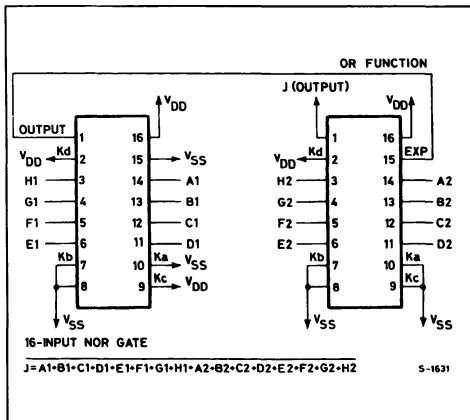
Note : (EXP) designates the EXPAND function (i.e., $X_1 + X_2 + \dots + X_N$).

APPLICATIONS OF EXPAND INPUT (continued)

12-Input or/and Gate.

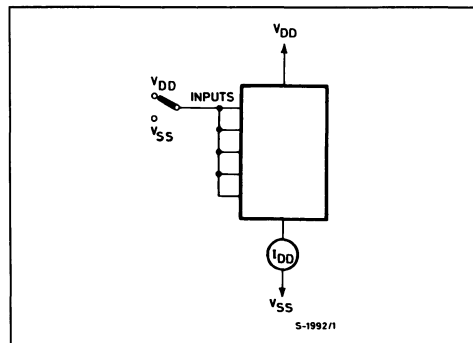


16-Input Nor Gate.

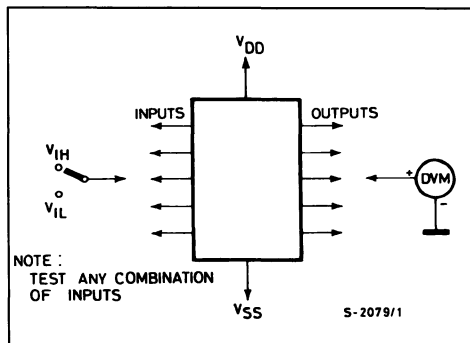


TEST CIRCUITS

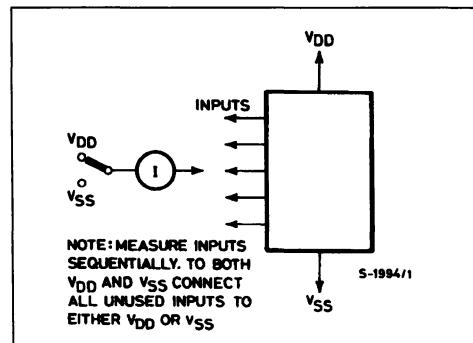
Quiescent Device Current.



Input Voltage.

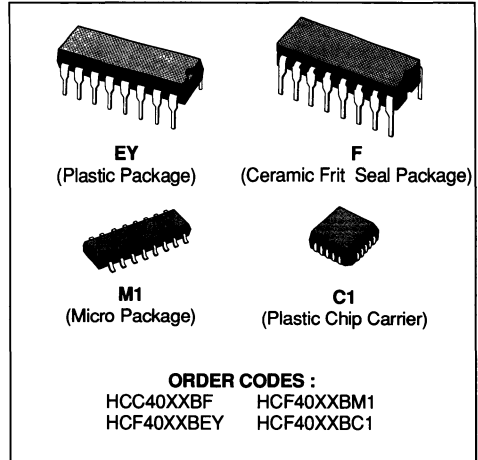


Input Current.



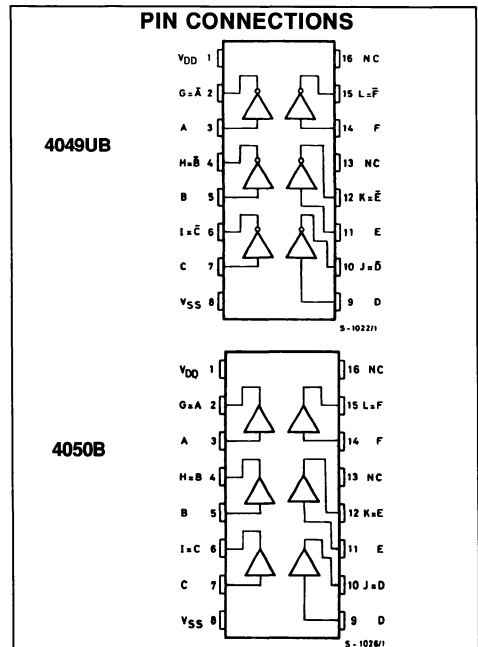
HEX BUFFER/CONVERTERS
4049UB INVERTING TYPE
4050B NON-INVERTING TYPE

- HIGH SINK CURRENT FOR DRIVING 2 TTL LOADS
- HIGH-TO-LOW LEVEL LOGIC CONVERSION
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- HIGH "SINK" AND "SOURCE" CURRENT CAPABILITY
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

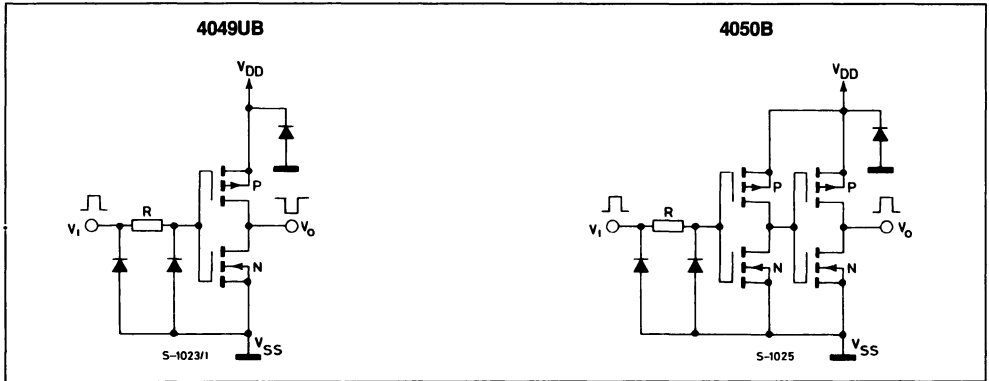

DESCRIPTION

The **HCC4049UB/4050B** (extended temperature range) and the **HCF4049UB/4050B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4049UB/4050B** are inverting and non-inverting hex buffers, respectively, and feature logic-level conversion using only one supply voltage (V_{DD}). The input-signal high level (V_{IH}) can exceed the V_{DD} supply voltage when these devices are used for logic level conversions. These devices are intended for use as COS/MOS to DTL/TTL converters and can drive directly two DTL/TTL loads ($V_{DD} = 5V$, $V_{OL} \leq 0.4V$, and $I_{OL} \geq 3.2mA$).



SCHEMATIC DIAGRAMS (1 of 6 identical units)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{Tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

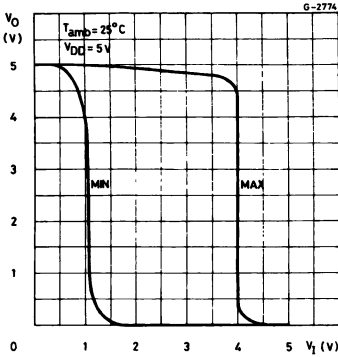
Symbol	Parameter		Test Conditions			Value						Unit	
			V _I (V)	V _O (V)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Supply Current	HCC Types	0/ 5		5		1		0.02	1		30	μA
			0/10		10		2		0.02	2		60	
			0/15		15		4		0.02	4		120	
		HCF Types	0/20		20		20		0.04	20		600	
			0/ 5		5		4		0.02	4		30	
			0/10		10		8		0.02	8		60	
0/15		15		16		0.02	16		120				
V _{OH}	Output High Voltage	0/ 5		5	4.95		4.95			4.95		V	
		0/10		10	9.95		9.95			9.95			
		0/15		15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		5		0.05			0.05		0.05	V	
		10/0		10		0.05			0.05		0.05		
		15/0		15		0.05			0.05		0.05		
V _{IH}	Input High Voltage (4049UB)		0.5	5	4		4			4		V	
			1	10	8		8			8			
			2	15	12		12			12			
V _{IH}	Input High Voltage (4050B)		4.5	5	3.5		3.5			3.5		V	
			9	10	7		7			7			
			13.5	16	11		11			11			
V _{IL}	Input Low Voltage (4049UB)		4.5	5		1			1		1	V	
			9	10		2			2		2		
			13	15		3			3		3		
V _{IL}	Input Low Voltage (4050B)		0.5	5		1.5			1.5		1.5	V	
			1	10		3			3		3		
			1.5	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5	5	1.6		-1.25	-6.4		-0.9	mA	
			0/ 5	4.6	5	0.64		-0.51	-1.6		-0.36		
			0/10	9.5	10	1.6		-1.30	-3.6		-0.9		
		0/15	13.5	15	4.7		-3.75	-12		-2.7			
		HCF Types	0/ 5	2.5	5	1.5		-1.25	-6.4		-1		
			0/ 5	4.6	5	0.61		-0.51	-1.6		-0.42		
0/10	9.5		10	1.5		-1.25	-3.6		-1				
0/15	13.5	15	4.5		-3.75	-12		-3					
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4	5	3.75		3.2	6.4		2.2	mA	
			0/10	0.5	10	10		8	16		5.6		
			0/15	1.5	15	30		24	48		17		
		HCF Types	0/ 5	0.4	5	3.6		3.2	6.4		2.6		
			0/10	0.5	10	9.6		8	16		6.6		
			0/15	1.5	15	28		24	48		19		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18		18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μA
		HCF Types	0/15		15		± 0.3		±10 ⁻⁵	± 0.3		± 1	
C _I	Input Capacitance	4049UB 4050B	Any Input						15 5	22.5 7.5		pF	

(*) T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.T_{High} = + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin (only HCC/HCF4050B type) for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

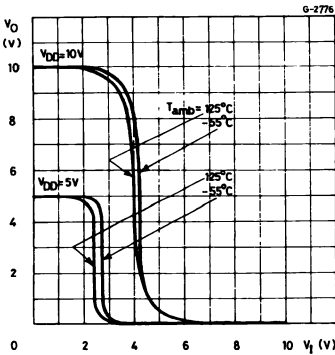
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit		
		V_I (V)	V_{DD} (V)	Min.	Typ.	Max.			
t_{PLH}	Propagation Delay Time (4049UB)			5	5		60	120	ns
				10	10		32	65	
				10	5		45	90	
				15	15		25	50	
				15	5		45	90	
t_{PLH}	Propagation Delay Time (4050B)			5	5		70	140	ns
				10	10		40	80	
				10	5		45	90	
				15	15		30	60	
				15	5		40	80	
t_{PHL}	Propagation delay Time (4049UB)			5	5		32	65	ns
				10	10		20	40	
				10	5		15	30	
				15	15		15	30	
				15	5		10	20	
t_{PHL}	Propagation Delay Time (4050B)			5	5		55	110	ns
				10	10		22	55	
				10	5		50	100	
				15	15		15	30	
				15	5		50	100	
t_{TLH}	Transition Time			5	5		80	160	ns
				10	10		40	80	
				15	15		30	60	
t_{THL}	Transition Time			5	5		30	60	ns
				10	10		20	40	
				15	15		15	30	

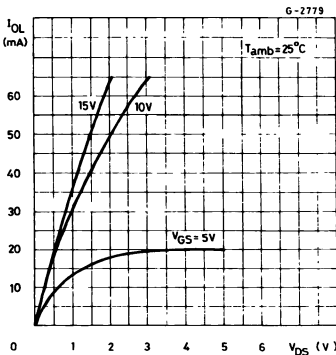
Minimum and Maximum Voltage Transfer Characteristics for 4049UB.



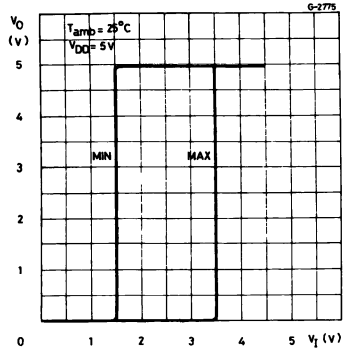
Typical Voltage Transfer Characteristics as a Function of Temperature for 4049UB.



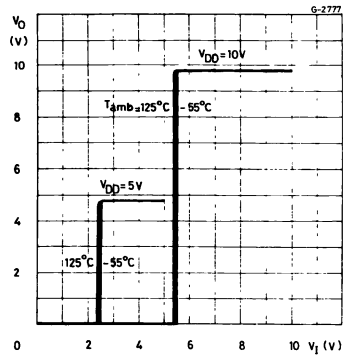
Typical Output Low (sink) Current Characteristics.



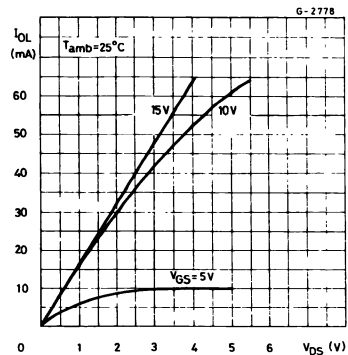
Minimum and Maximum Voltage Transfer Characteristics for 4050B.



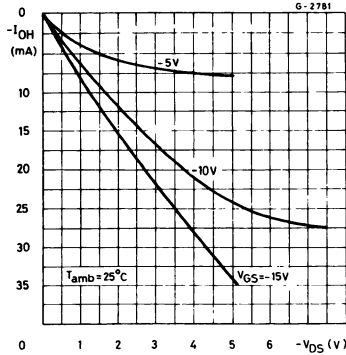
Typical Voltage Transfer Characteristics as a Function of Temperature for 4050B.



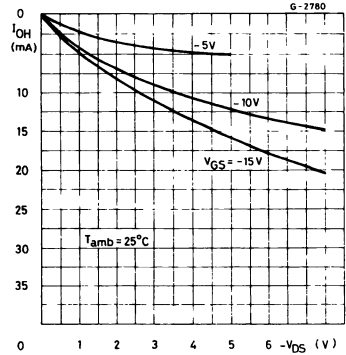
Minimum Output Low (sink) Current Characteristics.



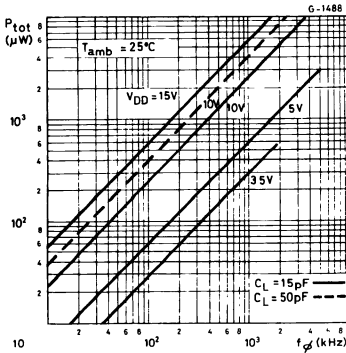
Typical Output High (source) Current Characteristics.



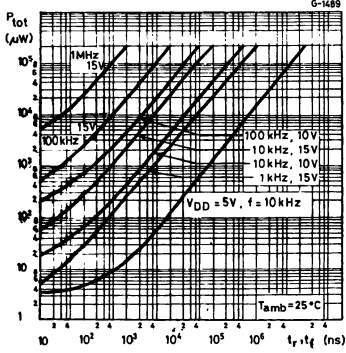
Minimum Output High (source) Current Characteristics.



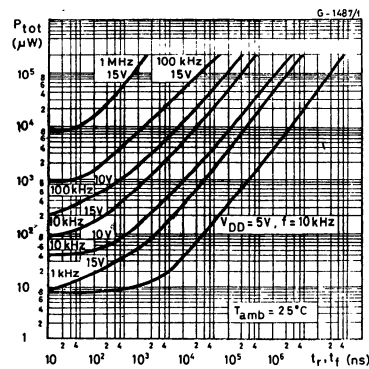
Typical Power Dissipation per Buffer/Inverter vs. Frequency.



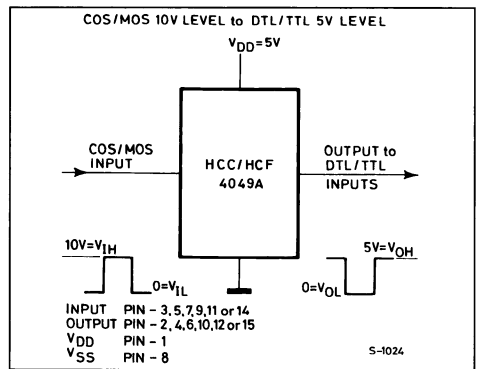
Typical Power Dissipation vs. Input Transition Time per Inverter for 4049UB.



Typical Power Dissipation vs. Input Transition Time per Inverter for 4050B.

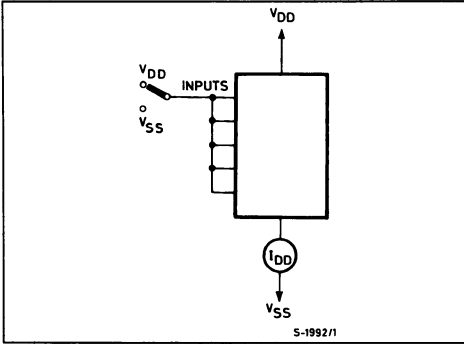


Logic-Level Conversion Application.

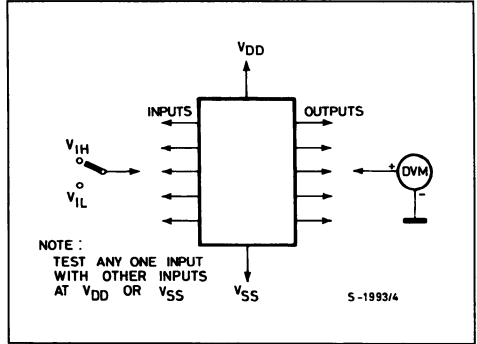


TEST CIRCUITS

Quiescent Device Current.

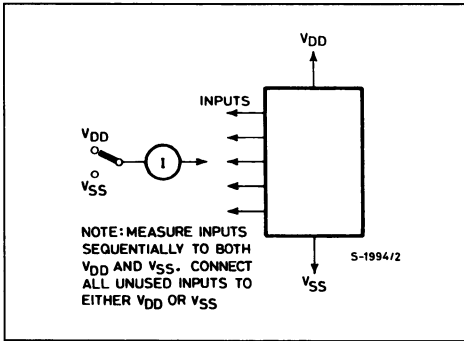


Input Voltage.



NOTE:
TEST ANY ONE INPUT
WITH OTHER INPUTS
AT V_{DD} OR V_{SS}

Input Current.



NOTE: MEASURE INPUTS
SEQUENTIALLY TO BOTH
V_{DD} AND V_{SS}. CONNECT
ALL UNUSED INPUTS TO
EITHER V_{DD} OR V_{SS}

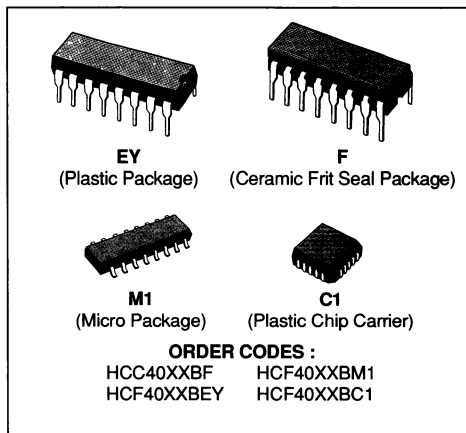
ANALOG MULTIPLEXERS-DEMULTIPLEXERS

4051B - SINGLE 8-CHANNEL

4052B - DIFFERENTIAL 4-CHANNEL

4053B - TRIPLE 2-CHANNEL

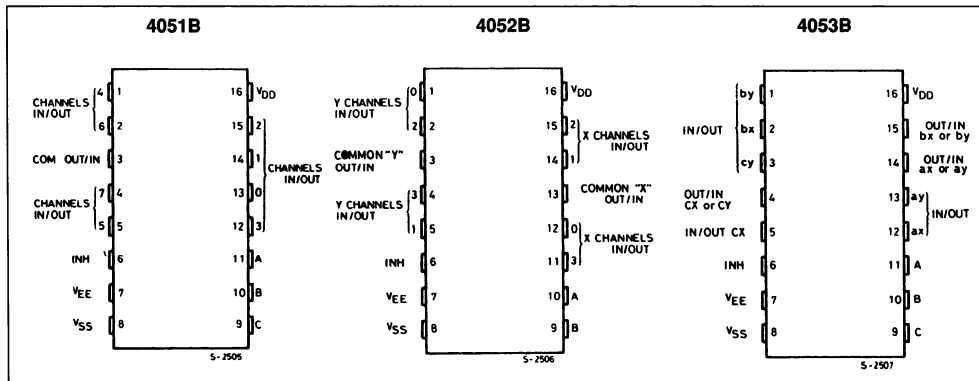
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- LOW "ON" RESISTANCE : 125Ω (typ.) OVER 15V p.p. SIGNAL-INPUT RANGE FOR $V_{DD} - V_{EE} = 15V$
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE $\pm 100pA$ (typ.) $V_{DD} - V_{EE} = 18V$
- BINARY ADDRESS DECODING ON CHIP
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS : 0.2 μW (typ.), $V_{DD} - V_{SS} = V_{DD} - V_{EE} = 10V$
- MATCHED SWITCH CHARACTERISTICS : $R_{ON} = 5\Omega$ (typ.) for $V_{DD} - V_{EE} = 15V$
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS : DIGITAL 3 TO 20V, ANALOG TO 20V p.p.
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100mA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC 4051B, 4052B** and **4053B** (extended temperature range) and **HCF4051B, 4052B** and **4053B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage. **HCC/HCF4051B, HCC/HCF4052B,** and **HCC/HCF4053B** analog multiplexers/demultiplexers are digitally controlled analog switches having low ON impedance and very low OFF

PIN CONNECTIONS



leakage current. These multiplexer circuits dissipate extremely low quiescent power over the full $V_{DD} - V_{SS}$ and $V_{DD} - V_{EE}$ supply-voltage ranges, independent of the logic state of the control signals. When a logic "1" is present at the inhibit input terminal all channel are off. The **HCC/HCF4051B** is a single 8-channel multiplexer having three binary control inputs, A, B, and C, and an inhibit input. The three binary signals select 1 of 8 channels to be turned on, and connect one of the 8 inputs to the output. The **HCC/HCF4052B** is a differential 4-channel

multiplexer having two binary control inputs, A and B, and an inhibit input. The two binary input signals select 1 of 4 pairs of channels to be turned on and connect the analog inputs to the outputs. The **HCC/HCF4053B** is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a singlepole double-throw configuration.

FUNCTIONAL DIAGRAMS AND TRUTH TABLES

4051B

Input States				"On" Channel (S)
Inhibit	C	B	A	
0	0	0	0	0
0	0	0	1	1
0	0	1	0	2
0	0	1	1	3
0	1	0	0	4
0	1	0	1	5
0	1	1	0	6
0	1	1	1	7
1	X	X	X	None

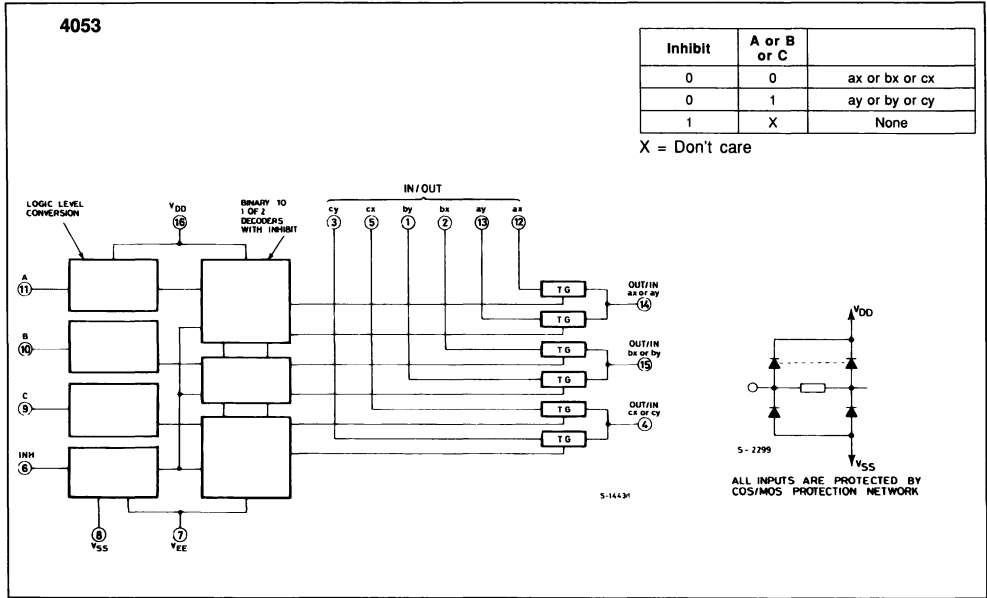
5 - 2299
ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

4052B

Inhibit	B	A	
0	0	0	0x, 0y
0	0	1	1x, 1y
0	1	0	2x, 2y
0	1	1	3x, 3y
1	X	X	None

5 - 2299
ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

FUNCTIONAL DIAGRAMS AND TRUTH TABLES (continued)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)


Symbol	Parameter		Test Conditions				Value						Unit							
			V _{IS} (V)	V _{EE} (V)	V _{SS} (V)	V _{DD} (V)	T _{L,low} *		25 °C			T _{H,high} *								
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.						
I _L	Quiescent Device Current	HCC Types				5		5		0.04	5		150							
						10		0.04	10		300									
						15		0.04	20		600									
						20		0.08	100		3000									
	HCF Types	5					0.04	20		150										
		10					0.04	40		300										
			15		0.04	80		600												
SWITCH																				
ON	Resistance	HCC Types	0 ≤ V _I ≤ V _{DD}	0	0	5		880		470	1050		1200							
						10		310		180	400		580							
						15		220		125	280		400							
		HCF Types				5		880		470	1050		1200							
						10		330		180	400		520							
						15		230		125	280		360							
ΔON	Resistance ΔR _{ON} (between any 2 channels)		0	0	5				10											
					10				10											
					15				5											
OFF (*) Channel Leakage Current	Any Channel OFF	HCC Types	0	0	18	100		± 0.1	100		1000	nA								
													All Channels OFF (common OUT/IN)	HCC Types	0	0	18	100	± 0.1	100
	Any Channel OFF	HCF Types																		
													All Channels OFF (common OUT/IN)	HCF Types	0	0	15	300	± 0.1	300
C Capacitance	Input								5											
	Output 4051								30											
	Output 4052								18											
	Output 4053								9											
	Feedthrough								0.2											
CONTROL (Address or Inhibit)																				
V _{IL}	Input Low Voltage		= V _{DD} Thru 1KΩ	V _{EE} = V _{SS} R _L = 1KΩ I _{IS} < 2μA (on all off channels)	5		1.5			1.5		1.5								
					10		3		3		3									
					15		4		4		4									
					5	3.5		3.5		3.5										
V _{IH}	Input High Voltage				10	7		7			7									
					15	11		11			11									
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	V _I = 0/18V		18		± 0.1		±10 ⁻³	± 0.1		± 1								
		HCF Types			V _I = 0/15V	15		± 0.3		±10 ⁻³	± 0.3		± 1							
C _I	Input Capacitance		Any Address or Inhibit Input						5	7.5		pF								

(*) Determined by minimum feasible leakage measurement for automatic testing

(*) T_{L,low} = - 55°C for HCC device ; - 40°C for HCF device

(*) T_{H,high} = + 125°C for HCC device ; + 85°C for HCF device

DYNAMIC ELECTRICAL CHARACTERISTICS(T_{amb} = 25°C, C_L = 50pF all input square wave rise and fall time = 20ns)

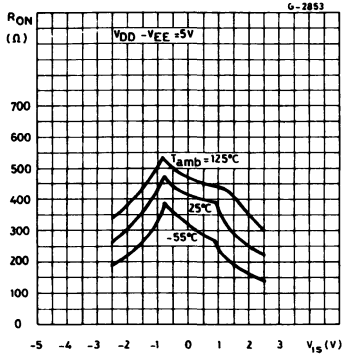
Parameter	Test Conditions						Value		Unit		
	V _{EE} (V)	R _L (kΩ)	f _i (kHz)	V _{IS} (V)	V _{SS} (V)	V _{DD} (V)	Typ.	Max.			
SWITCH											
t _{pd} Propagation Delay Time (signal input to output)		200		10 V 		5		30	30	ns	
								15	60		
								11	20		
Frequency Response Channel "ON" (sine wave input) at 20 Log $\frac{V_o}{V_i} = -3dB$	= V _{SS}	1		5 (•)		10	V _o at Common OUT/IN	4053B	30	MHz	
								4052B	25		
								4051B	20		
						V _o at any Channel		60			
Feedthrough (all channels OFF) at 20 Log $\frac{V_o}{V_i} = -40dB$	= V _{SS}	1		5 (•)		10	V _o at Common OUT/IN	4053	8	MHz	
								4052	10		
								4051	12		
						V _o at any Channel		8			
Frequency Signal Crosstalk at 20 Log $\frac{V_o}{V_i} = -40dB$	= V _{SS}	1		5 (•)		10	Between any 2 Channels		3	MHz	
							Between Sections 4052B only	measured on common any channel	6		
									10		
							Between any 2 Sections 4053B only	irPir2 outPin4	2.5		MHz
irPir15 outPin4	6										
Sine Wave Distortion f _{is} = 1kHz Sine Wave	= V _{SS}	10	1	2 (•)		5		0.3	%		
								10		0.2	
								10		1	5 (•)
CONTROL (Address or Inhibit)											
Propagation Delay Time : Address-to Signal OUT Channels ON or OFF	0					0	5		360	720	ns
									160	320	
									120	240	
								- 5	0	5	
Propagation Delay Time : Inhibit to Signal OUT (channel turning ON)	0	10				0	5		360	720	ns
									160	320	
									120	240	
								- 10	0	5	
Propagation Delay Time : Inhibit to Signal OUT (channel turning OFF)	0	0.3					5		200	450	ns
									90	210	
									70	160	
								- 10		5	
Address or Inhibit to Signal Crosstalk	0	10*				0	10	V _C = V _{DD} -V _{SS} (square wave)	65		mV peak

(•) Peak to peak voltage symmetrical about V_{DD}-V_{EE}

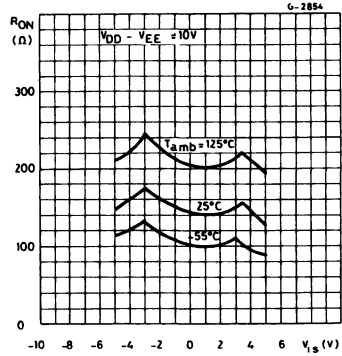
2

(*) Both ends of channel

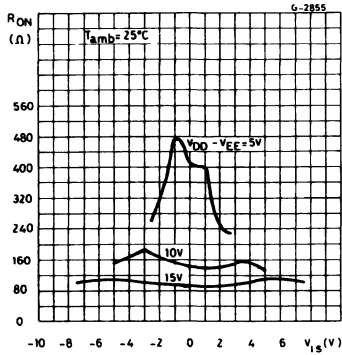
Typical Channel ON Resistance vs. Input Signal Voltage (all types).



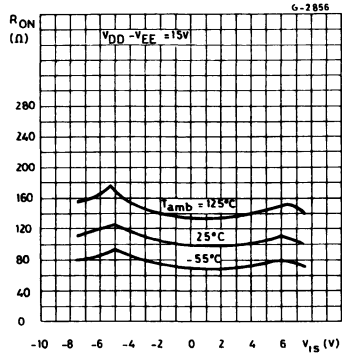
Typical Channel ON Resistance vs. Input Signal Voltage (all types).



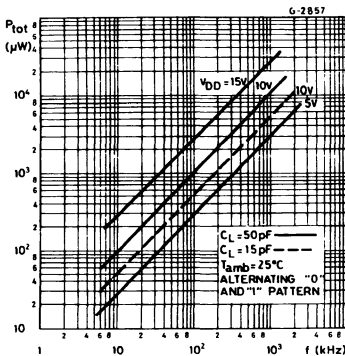
Typical Channel ON Resistance vs. Input Signal Voltage (all types).



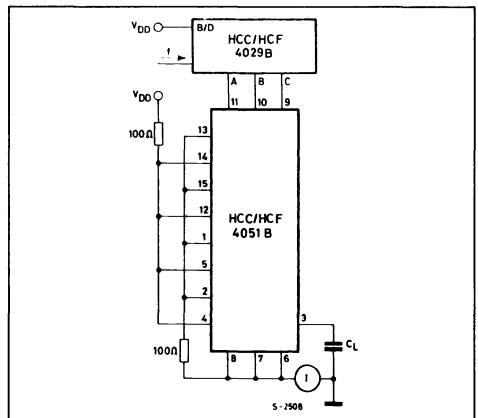
Typical Channel ON Resistance vs. Input Signal Voltage (all types).



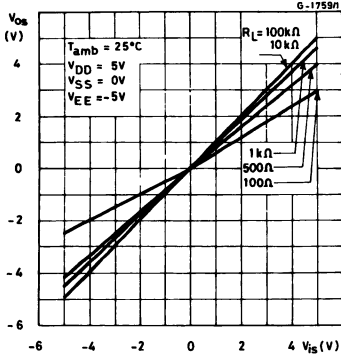
Typical Dynamic Power Dissipation/Package vs.



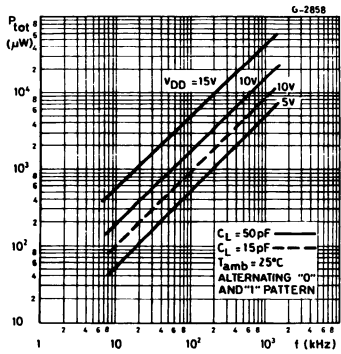
Switching Frequency and Test Circuit (4051B).



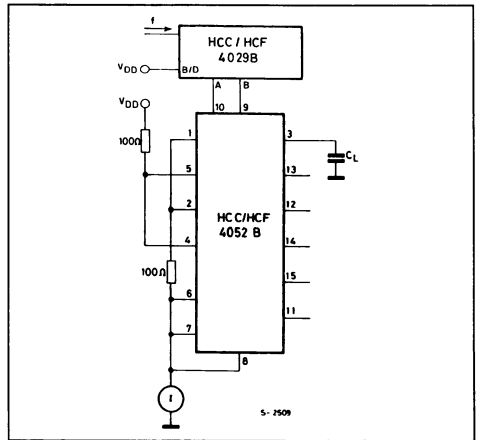
Typical ON Characteristics for 1 of 8 Channels (4051B).



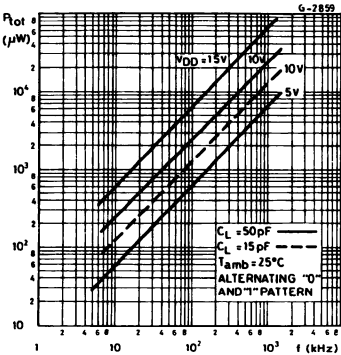
Typical Dynamic Power Dissipation/Package vs.



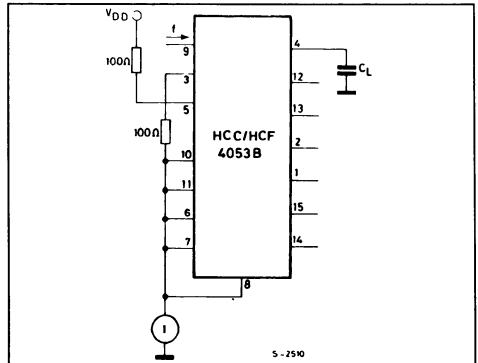
Switching Frequency and Test Circuit (4052B).



Typical Dynamic Power Dissipation/Package vs.

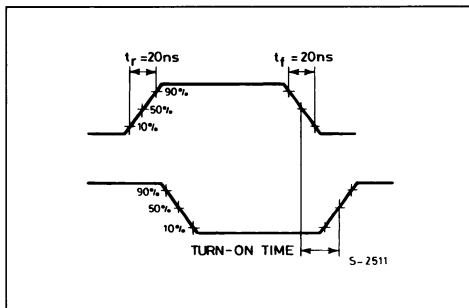


Switching Frequency and Test Circuit (4053B).

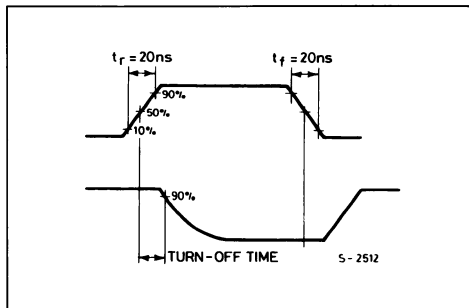


WAVEFORMS

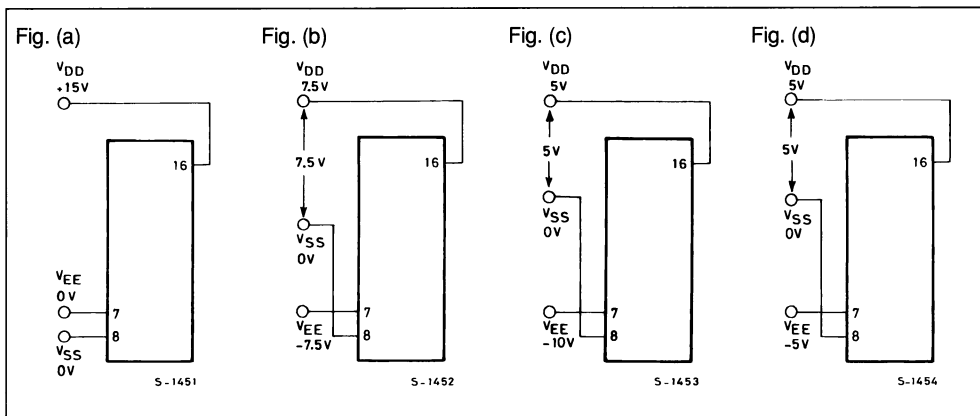
Channel Being Turned ON ($R_L = 10K\Omega$).



Channel Being Turned OFF ($R_L = 300K\Omega$).



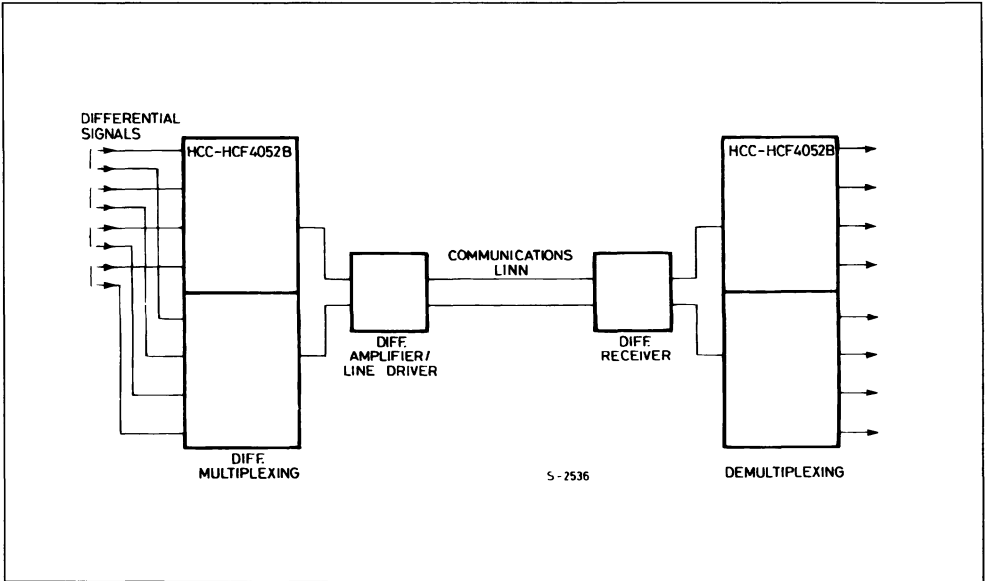
TYPICAL BIAS VOLTAGES



The ADDRESS (digital-control inputs) and INHIBIT logic levels are "0"= V_{SS} and "1"= V_{DD} . The analog signal (through the TG) may swing from V_{EE} to V_{DD}

TYPICAL APPLICATIONS

TYPICAL TIME-DIVISION APPLICATION OF THE 4052B



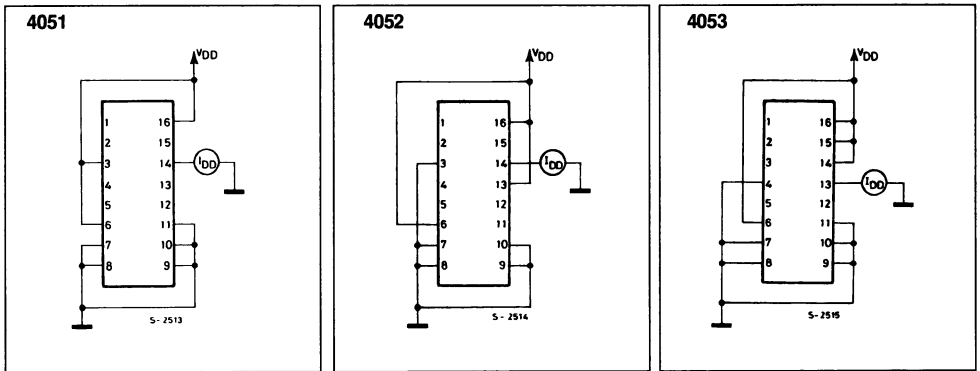
SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak-to-peak can be achieved by digital signal amplitudes of 4.5 to 20V (if $V_{DD} - V_{SS} = 3V$, a $V_{DD} - V_{EE}$ of up to 13V can be controlled ; for $V_{DD} - V_{EE}$ level differences above 13V, a $V_{DD} - V_{SS}$ of at least 4.5V is required). For example, if $V_{DD} = +5V$, $V_{SS} = 0$, and $V_{EE} = -13.5V$, analog signals from $-13.5V$ to $+4.5V$ can be controlled by digital inputs of 0 to 4.5V. In certain applications, the external load-resistor current may include both V_{DD} and signal-line components. To

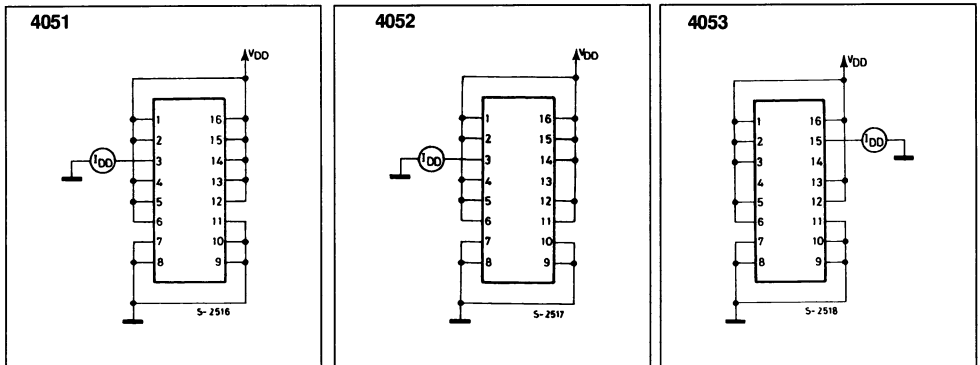
avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8 volt (valuated from R_{ON} values shown in ELECTRICAL CHARACTERISTICS CHART). No V_{DD} current will flow through R_L if the switch current flows into lead 3 on the **HCC/HCF4051** ; leads 3 and 13 on the **HCC/HCF4052** ; leads 4, 14, and 15 on the **HCC/HCF4053**.

TEST CIRCUITS

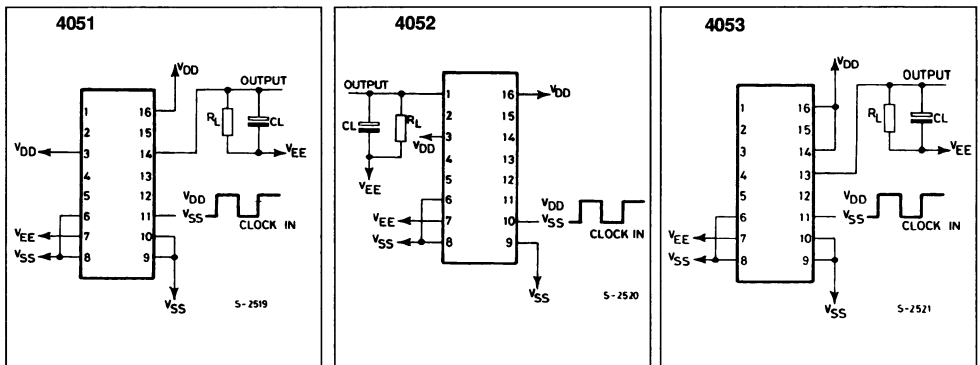
Off Channel Leakage Current-any Channel OFF.



Off Channel Leakage Current-all Channel OFF.

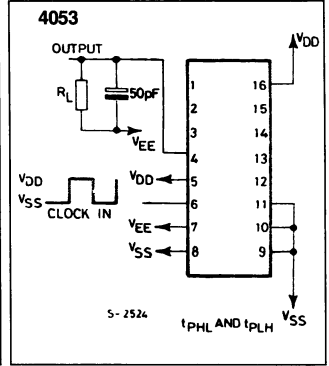
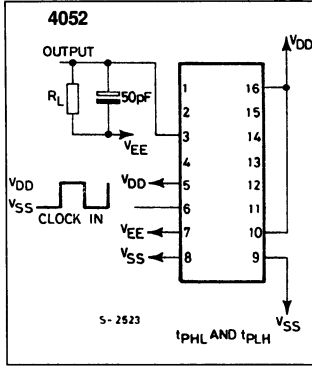
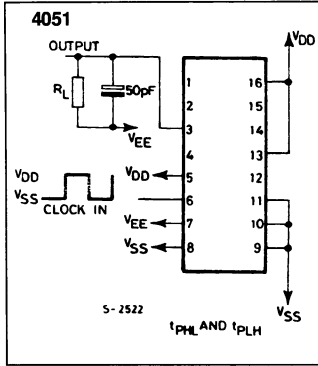


Propagation Delay-address Input to Signal Output.

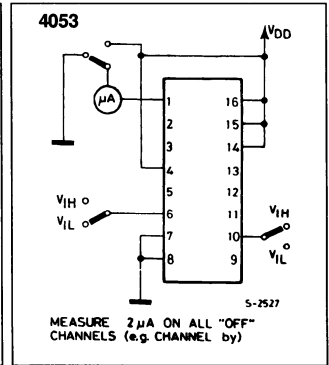
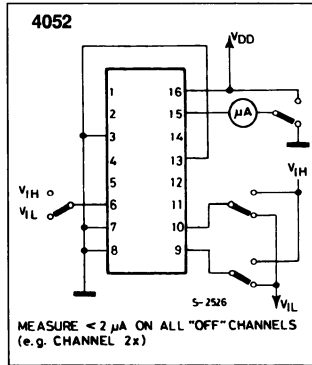
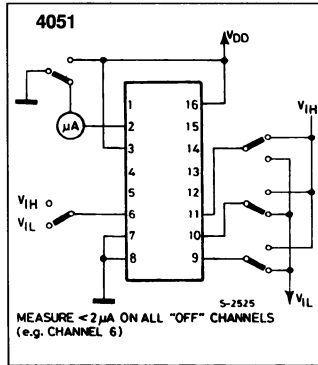


TEST CIRCUITS (continued)

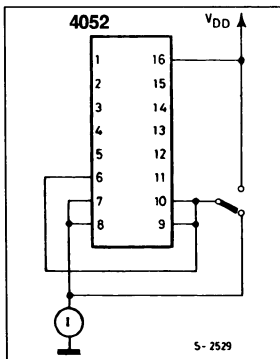
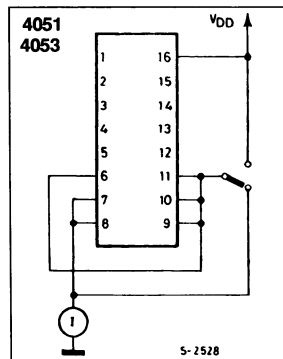
Propagation Delay-Inhibit Input to Signal Output.



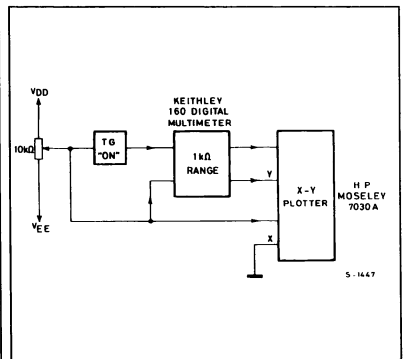
Input Voltage.



Quiescent Device Current.

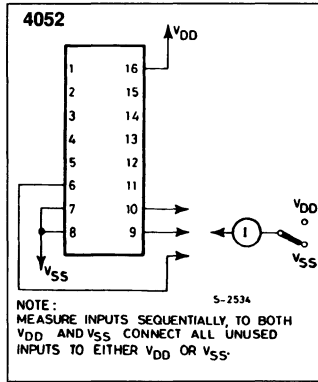
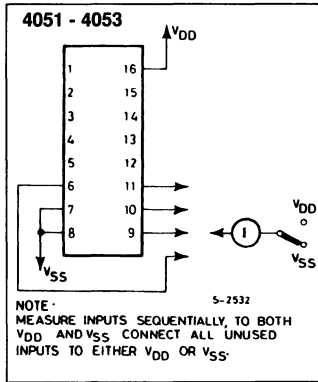


Channel ON Resistance Measurement Circuit.

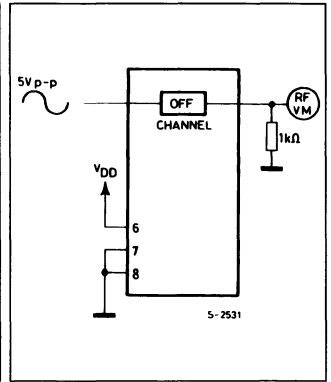


TEST CIRCUITS (continued)

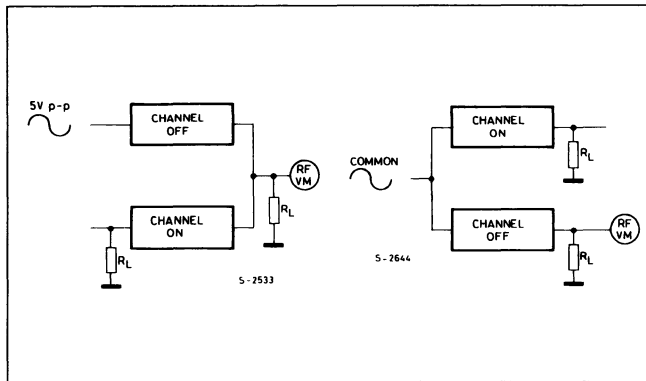
Input Current.



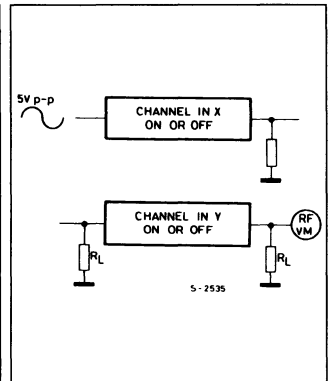
Feedthrough (All Types).



Crosstalk Between any two Channels (All Types).



Crosstalk Between Duals or Triplets (4052-4053).



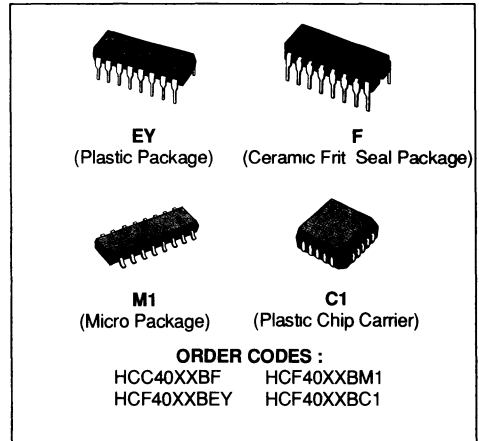
LIQUID-CRYSTAL DISPLAY DRIVERS

4054B 4-SEGMENT DISPLAY DRIVER - STROBED LATCH FUNCTION
4055B BCD TO 7-SEGMENT DECODER/DRIVER, WITH "DISPLAY-FREQUENCY" OUTPUT
4056B BCD TO 7-SEGMENT DECODER/DRIVER WITH STROBED LATCH FUNCTION

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- OPERATION OF LIQUID CRYSTALS WITH COS/MOS CIRCUITS PROVIDES ULTRA-LOW-POWER DISPLAYS
- EQUIVALENT AC OUTPUT DRIVE FOR LIQUID-CRYSTAL DISPLAYS-NO EXTERNAL CAPACITOR REQUIRED
- VOLTAGE DOUBLING ACROSS DISPLAY [($V_{DD} - V_{EE}$) = 18V] RESULTS IN EFFECTIVE 36V (p-p) DRIVE ACROSS SELECTED DISPLAY SEGMENTS
- LOW-OR HIGH-OUTPUT LEVEL DC DRIVE FOR OTHER TYPES OF DISPLAYS
- ON-CHIP LOGIC-LEVEL CONVERSION FOR DIFFERENT INPUT AND OUTPUT-LEVEL SWINGS
- FULL DECODING OF ALL INPUT COMBINATIONS : "0 - 9, L, H, P, A- " AND BLANK POSITIONS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4054B**, **HCC4055B** and **HCC4056B** (extended temperature range) and the **HCF4054B**, **HCF4055B** and **HCF4056B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4055B** and **HCC/HCF4056B** types are single-digit BCD-to-7-segment decoder/driver circuits that provide level-shifting functions on the chip. This feature permits the BCD input-signal swings (V_{DD} to V_{SS}) to be the same as

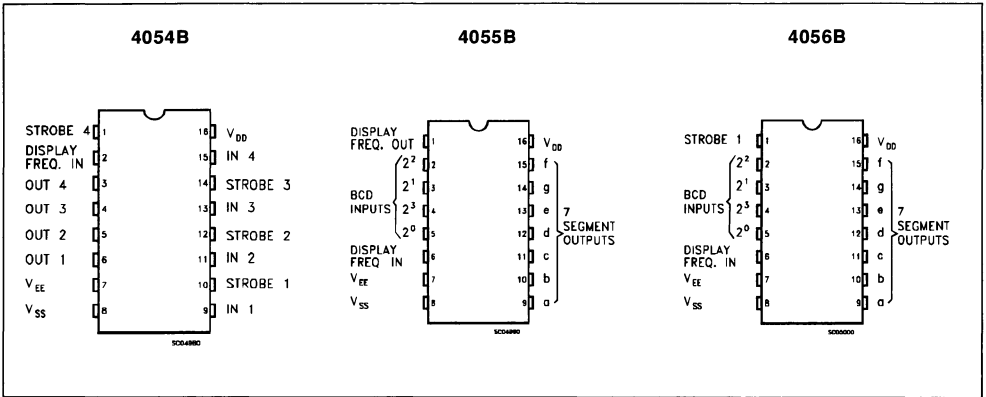


or different from the 7-segment output-signal swings (V_{DD} to V_{EE}). For example, the BCD input-signal swings (V_{DD} to V_{SS}) may be as low as 0 to -3V, whereas the output-display drive-signal swing (V_{DD} to V_{EE}) may be from 0 to -5V. If V_{DD} to V_{EE} exceeds 15V, V_{DD} to V_{SS} should be at least 4V. The 7-segment outputs are controlled by the DISPLAY-FREQUENCY (DF) input which causes the selected segment outputs to be low, high, or a square-wave output (for liquid-crystal displays). When the DF input is low the output segments will be high when selected by the BCD inputs. When the DF input is high, the output segments will be low when selected by the BCD inputs. When a square-wave is present at the DF input, the selected segments will have a square-wave output that is 180° out of phase with the DF input. Those segments which are not selected will have a square-wave output that is in phase with the input. DF square-wave repetition rates for liquid-crystal displays usually range from 30Hz (well above flicker rate) to 200Hz (well below the upper limit of the liquid-crystal frequency response). The **HCC/HCF4055B** provides a level-shifted high-amplitude DF output which is required for driving the common electrode in liquid-crystal displays. The **HCC/HCF4056B** provides a strobed-latch function at the BCD inputs. Decoding of all input combinations on the **HCC/HCF4055B** and **HCC/HCF4056B** provides displays of 0 to 9 as well

as L, P, H, A, - , and a blank position. (see typical application for other letters). The HCC/HCF4054B provides level shifting similar to the HCC/HCF4055B and HCC/HCF4056B independently strobed latches, and common DF control on 4 signal lines. The HCC/HCF4054B is intended to provide drive-signal compatibility with the HCC/HCF4055B and HCC/HCF4056B 7-segment decoder types for the decimal point, colon, polarity, and similar display lines. A level-shifted high-amplitude DF output can be obtained from any HCC/HCF4054B output line by connecting the corresponding input and strobe lines to a low and high level, respectively. The HCC/HCF4054B may also be utilized for logic-level "up conversion" or "down conversion". For example, input-signal swings (V_{DD} to V_{SS}) from + 5 to 0V can be converted to output-signal swings (V_{DD} to V_{EE}) of + 5 to - 5V. The level-shifted function on all three types permits the use of different input-and output-signal swings. The input swings from a low level of V_{SS} to a high level of V_{DD} while the output swings

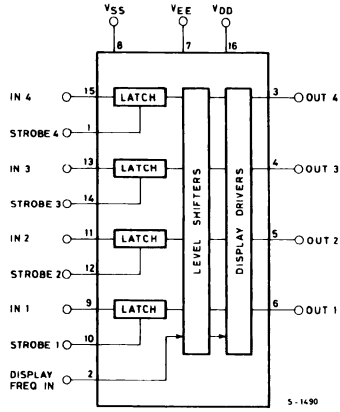
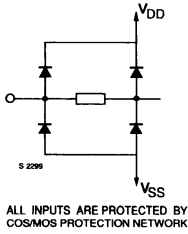
from a low level of V_{EE} to the same high level of V_{DD} . Thus, the input and output swings can be selected independently of each other over a 3-to-18V range. V_{SS} may be connected to V_{EE} when no level-shift function is required. For the HCC/HCF 4054B and HCC/HCF 4056B, data are transferred from input to output by placing a high voltage level at the strobe input. A low voltage level at the strobe input latches the data input and the corresponding output segments remain selected (or non-selected) while the strobe is low. Whenever the level-shifting function is required, the HCC/HCF4055B can be used by itself to drive a liquid-crystal display (fig. 10 and fig. 12). The HCC/HCF4056B, however, must be used together with a HCC/HCF4054B to provide the common DF output (fig. 14). The capability of extending the voltage swing on the negative end (this voltage cannot be extended on the positive end) can be used to advantage in the set-up of fig. 11. Fig. 9 is common to all three types.

PIN CONNECTIONS

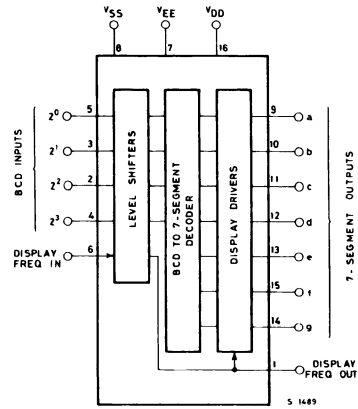
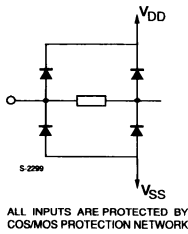


FUNCTIONAL DIAGRAMS

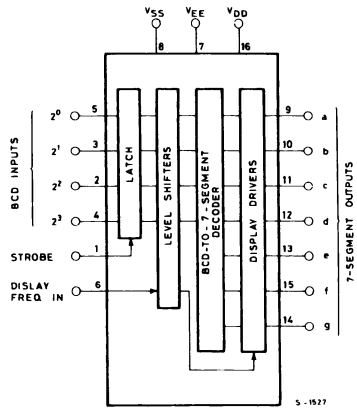
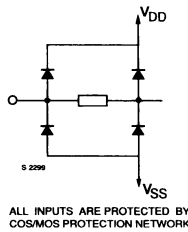
4054B



4055B



4056B



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

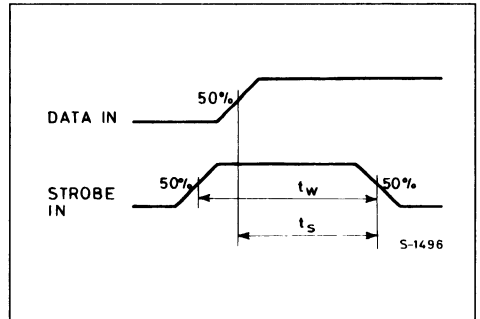
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to 125 - 40 to 85	°C °C

TRUTH TABLE

4055 B and 4056 B

Input Code				Output State							Display Character
2 ³	2 ²	2 ¹	2 ⁰	a	b	c	d	e	f	g	
0	0	0	0	1	1	1	1	1	1	0	0
0	0	0	1	0	1	1	0	0	0	0	0
0	0	1	0	1	1	0	1	1	0	1	2
0	0	1	1	1	1	1	1	0	0	1	3
0	1	0	0	0	1	1	0	0	1	1	4
0	1	0	1	1	0	1	1	0	1	1	5
0	1	1	0	1	0	1	1	1	1	1	6
0	1	1	1	1	1	1	1	0	0	0	7
1	0	0	0	1	1	1	1	1	1	1	8
1	0	0	1	1	1	1	1	0	1	1	9
1	0	1	0	0	0	0	1	1	1	0	L
1	0	1	1	0	1	1	0	1	1	1	H
1	1	0	0	1	1	0	0	1	1	1	P
1	1	0	1	1	1	1	0	1	1	1	A
1	1	1	0	0	0	0	0	0	0	1	-
1	1	1	1	0	0	0	0	0	0	0	BLANK

Data Setup Time and Strobe Pulse Duration.



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions					Value						Unit	
			V _{EE} (V)	V _I (V)	V _O (V)	V _{SS} (V)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
								Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Supply Current	HCC Types	-5	0/5		0	5		5		0.04	5		150	μA
			0	0/10		0	10		10		0.04	10		300	
			0	0/15		0	15		20		0.04	20		600	
			0	0/20		0	20		100		0.08	100		3000	
		HCF Types	-5	0/5		0	5		20		0.04	20		150	
			0	0/10		0	10		40		0.04	40		300	
V _{OH}	Output High Voltage		0	0/5		0	5	4.95		4.95			4.95	V	
			0	0/10		0	10	9.95		9.95			9.95		
			0	0/15		0	15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage		0	5/0		0	5		0.05			0.05	0.05	V	
			0	10/0		0	10		0.05			0.05	0.05		
			0	15/0		0	15		0.05			0.05	0.05		
V _{IH}	Input High Voltage		-5		0.5/4.5	0	5	3.5		3.5			3.5	V	
			0		1/9	0	10	7		7			7		
			0		15/18.5	0	15	11		11			11		
V _{IL}	Input Low Voltage		5		0.5/4.5	0	5		1.5			1.5	1.5	V	
			0		9/1	0	10		3			3	3		
			0		15/18.5	0	15		4			4	4		
I _{OH}	Output High Current	HCC Types	-5	0/5	4.5	0	5	-0.6		-0.45	-0.9		-0.3	mA	
			0	0/10	9.5	0	10	-0.6		-0.45	-0.9		-0.3		
			0	0/15	13.5	0	15	-1.9		-1.5	-3		-1.1		
		HCF Types	-5	0/5	4.5	0	5	-0.47		-0.38	-0.9		-0.28		
			0	0/10	9.5	0	10	-0.47		-0.38	-0.9		-0.28		
			0	0/15	13.5	0	15	-1.58		-1.27	-3		-0.95		
I _{OL}	Output Low Current	HCC Types	-5	0/5	0.4	0	5	1.6		1.3	2.6		0.9	mA	
			0	0/10	0.5	0	10	1.6		1.3	2.6		0.9		
			0	0/15	1.5	0	15	4.2		3.4	6.8		2.4		
		HCF Types	-5	0/5	0.4	0	5	1.37		1.1	2.6		0.82		
			0	0/10	0.5	0	10	1.37		1.1	2.6		0.82		
			0	0/15	1.5	0	15	3.62		2.9	6.8		2.17		
I _{IH} , I _{IL} **	Input Leakage Current	HCC Types	0	0/18		0	18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μA
		HCF Types	0	0/15		0	15		± 0.3		±10 ⁻⁵	± 0.3		± 1	μA
C _I **	Input Capacitance									5	7.5			pF	

*T_{Low} = -55°C for HCC device ; -40°C for HCF device.*T_{High} = 125°C for HCC device ; +85°C for HCF deviceThe Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

** Any input

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions			Types						Unit
		V_{EE} (V)	V_{SS} (V)	V_{DD} (V)	4054B			4055B, 4056B			
					Min.	Typ.	Max.	Min.	Typ.	Max.	
t_{PHL}, t_{PLH}	Propagation Delay Time (any input to any output)	-5	0	5		400	800		650	1300	ns
		0	0	10		340	680		575	1150	
		0	0	15		250	500		375	750	
t_{THL}, t_{TLH}	Transition Time (any output)	-5	0	5		100	200		100	200	ns
		0	0	10		100	200		100	200	
		0	0	15		75	150		75	150	
t_{setup}^*	Data Setup Time	-5	0	5	220	110		220	110		ns
		0	0	10	100	50		100	50		
		0	0	15	70	35		70	35		
t_w^*	Strobe Pulse Width	-5	0	5	220	110		220	110		ns
		0	0	10	100	50		100	50		
		0	0	15	70	35		70	35		

* HCC/HCF4054B and HCC/HCF4056B only.

Figure 1 : Typical Output Low (sink) Current Characteristics.

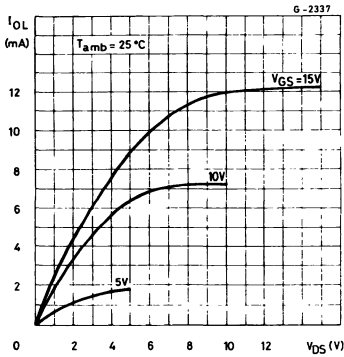


Figure 2 : Minimum Output High (source) Current Characteristics.

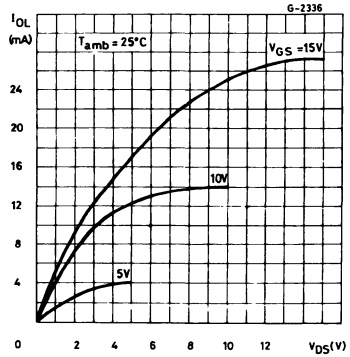


Figure 3 : Typical Output High (source) Current Characteristics.

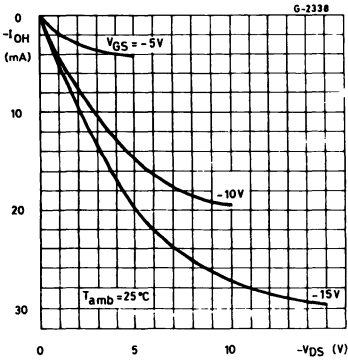


Figure 4 : Minimum Output (source) Current Characteristics.

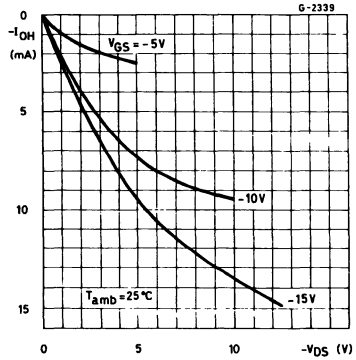


Figure 5 : Typical Propagation Delay Time vs. Load Capacitance (for 4054B).

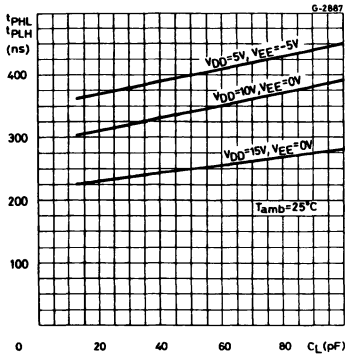


Figure 6 : Typical Propagation Delay Time vs. Load Capacitance (for 4055B and 4056B).

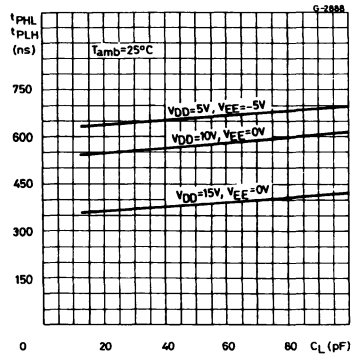


Figure 7 : Typical Transition Time vs. Load Capacitance.

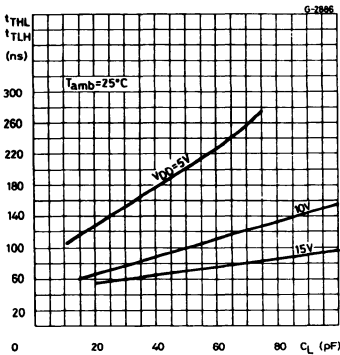
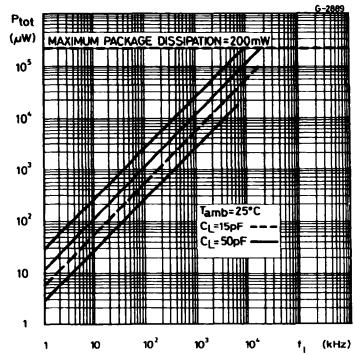


Figure 8 : Typical Dynamic Power Dissipation vs. Frequency.



TYPICAL APPLICATIONS

Figure 9 : Display-driver Circuit for one Segment Line and Waveforms.

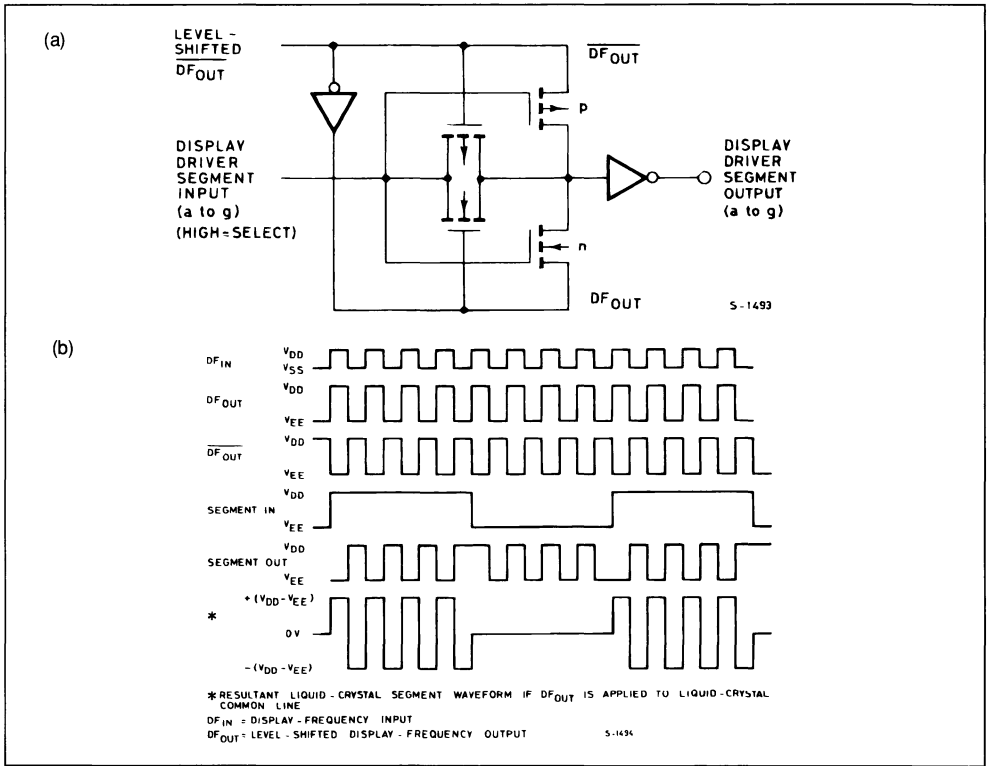
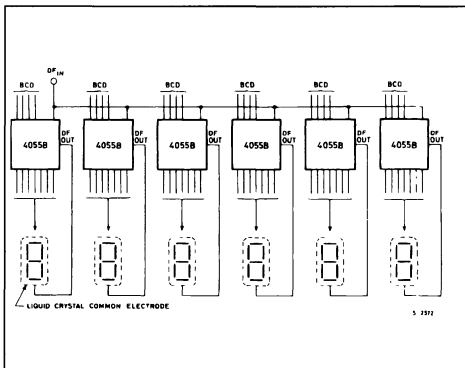
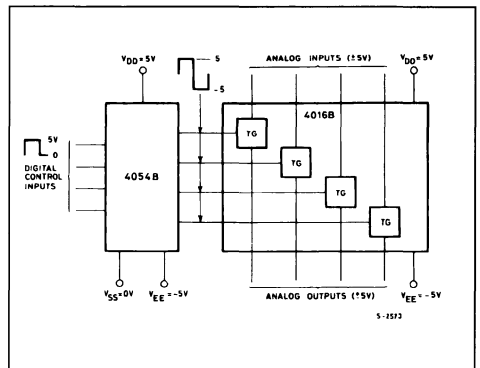


Figure 10 : Clock Display.



$V_{DD} = 0V$, $V_{SS} = -5V$, $V_{EE} = -15V$, $F_{IN} = 30$ Hz square wave

Figure 11 : Digital (0 to +5V) to bidirectional Analog Control (+5 to -5V) Level Shifter.



TYPICAL APPLICATIONS (continued)

Figure 12 : Single-digit Liquid Crystal Display.

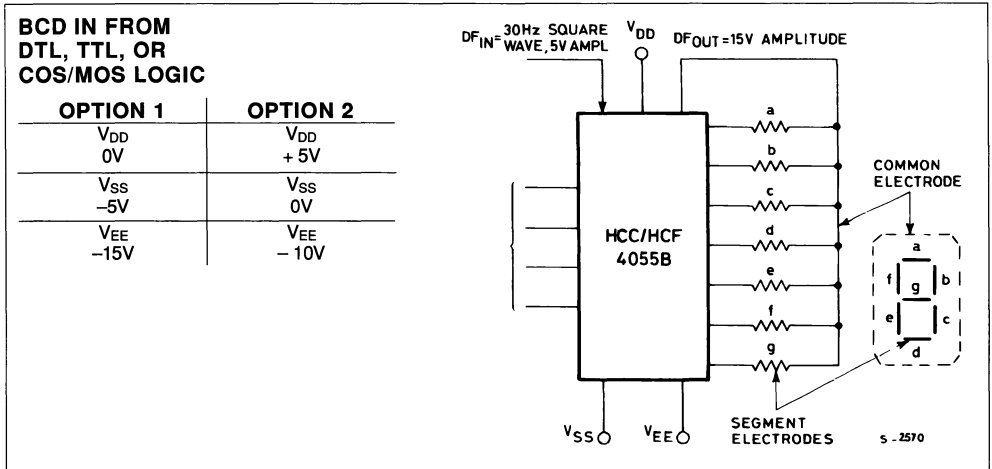
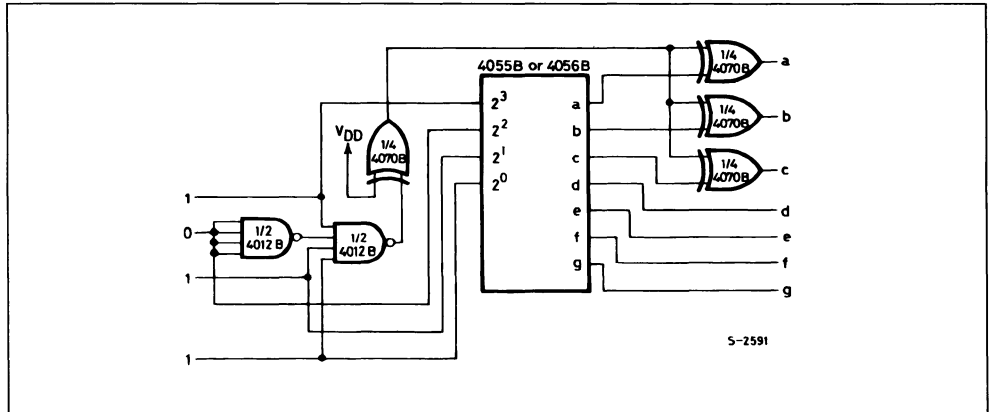
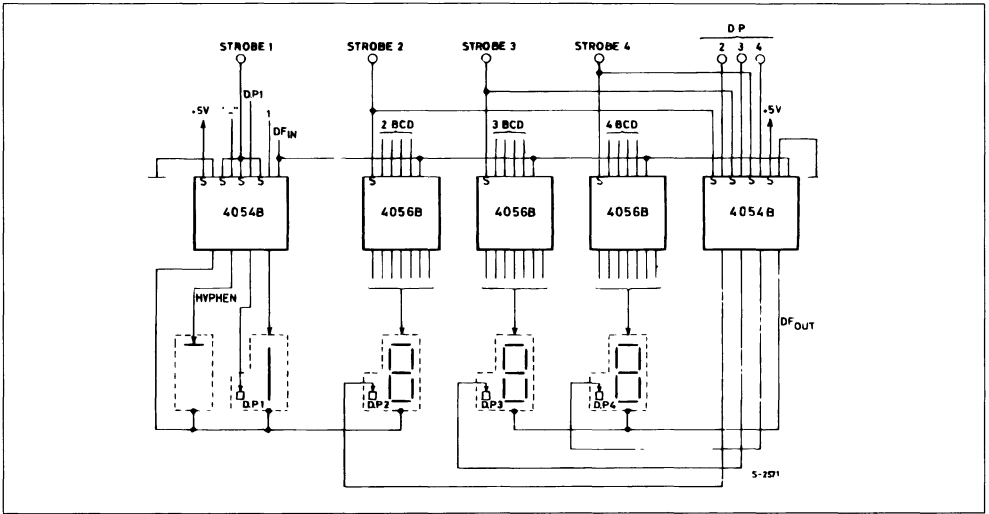


Figure 13 : Conversion of "H" Display to "F" Display.



TYPICAL APLLICATIONS (continued)

Figure 14 : Typical 3 1/2 – Digit–crystal Display : ($V_{DD} = +5V$, $V_{SS} = 0V$, $V_{EE} = -10V$, $DF_N = 30\text{ Hz square}$).



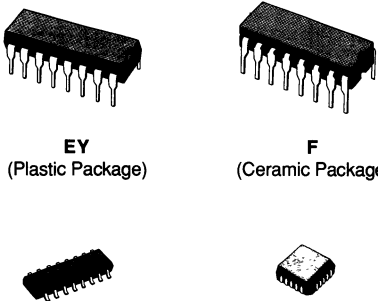
In addition to the letters L, H, P, and A, five other letters can be displayed through the use of simple logic circuits preceding and following the HCC/HCF4055B or HCC/HCF4056B devices. Fig. 13 is an example of a circuit that converts an "H" display, (code 1011) to an "F" display. One condition that must be met is that $V_{EE} = V_{SS}$. If $V_{EE} \neq V_{SS}$, the HCC/HCF4054B must be used to level shift in the

appropriate places. In a similar manner the letters C, E, J, and U can be displayed. These circuits can also be used to drive LED displays provided the exclusive-OR gates have sufficient output-current drive. The letters B, D, G, I, O, and S may be represented by the codes for numbers 8, 0, 6, 1, 0, and 5, respectively, when there is preknowledge that only letters are to be displayed.



**14-STAGE RIPPLE CARRY BINARY
COUNTER/DIVIDER AND OSCILLATOR**

- MEDIUM-SPEED OPERATION
- COMMON RESET
- FULLY STATIC OPERATION
- BUFFERED INPUTS AND OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 1005 TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF 'B' SERIES CMOS DEVICES "

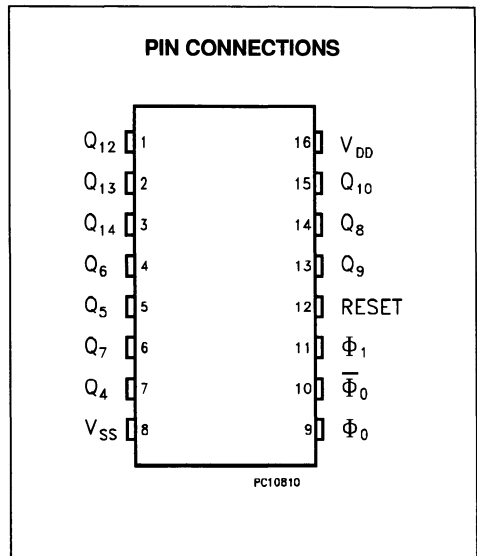


ORDER CODES :

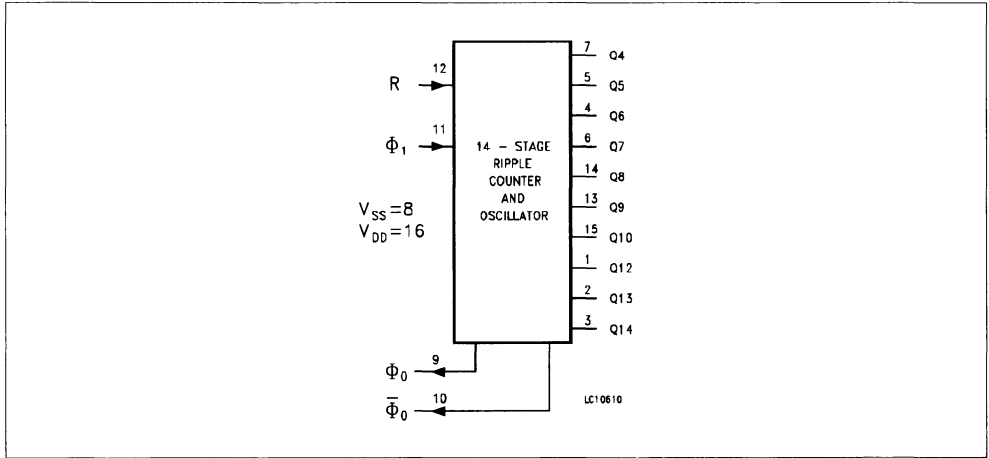
HCC4060BF	HCF4060BM1
HCF4060BEY	HCF4060BC1

DESCRIPTION

The **HCC4060B** (extended temperature range) and **HCF4060B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in line plastic or ceramic package and plastic micropackage. The **HCC/HCF4060B** consist of an oscillator section and 14 ripple carry binary counter stages. The oscillator configuration allows design of either RC or crystal oscillator circuits. A RESET input is provided which reset the counter to the all 0's state and disables oscillator. A high level on the RESET line accomplishes the reset function. All counter stages are master slave flip-flops. The state of the counter is advanced one step in binary order on the negative transition of ϕ_1 (and ϕ_0). All inputs and outputs are fully buffered. Schmitt trigger action on the clock lin permits unlimited clock rise and fall time.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
V_I	Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW mW
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$

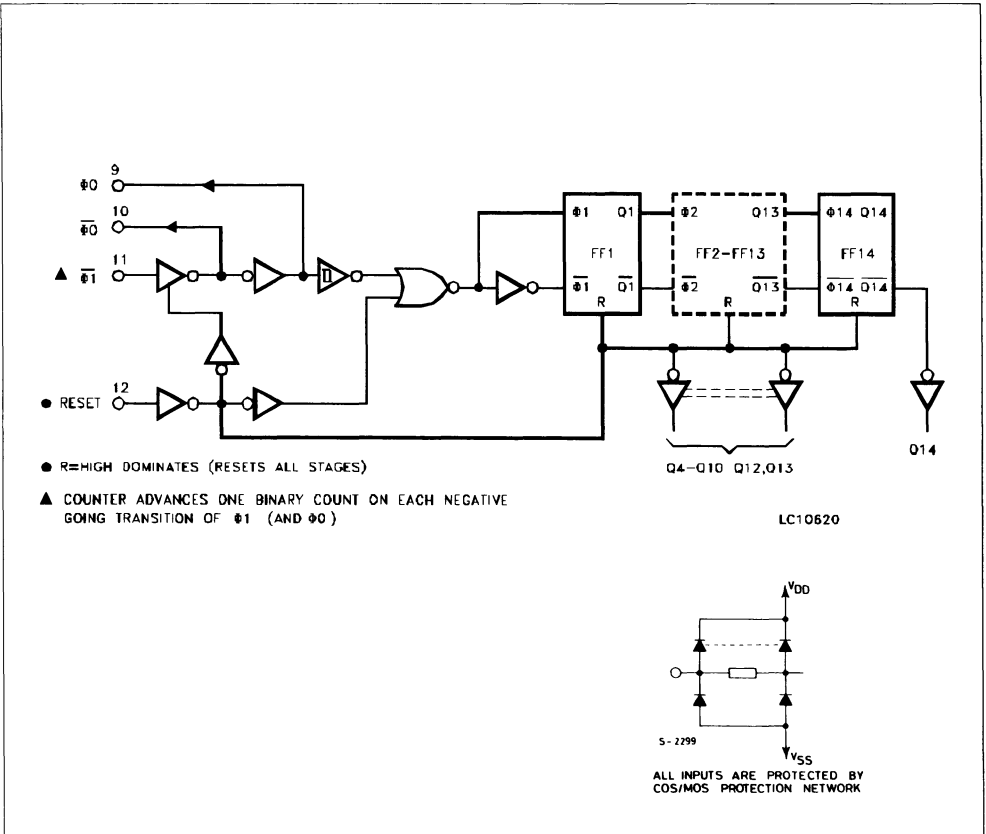
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	0/18			18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		0/15		Any Input	15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	μ A	
C _I	Input Capacitance			Any Input					5	7.5		pF		

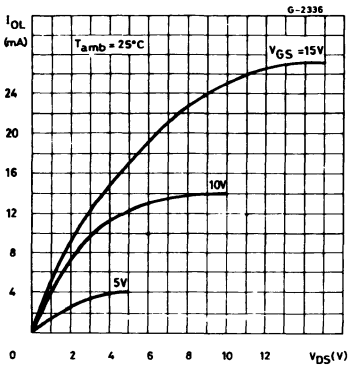
* T_{LOW} = -55 °C for HCC device -40 °C for HCF device* T_{HIGH} = +125 °C for HCC device +85 °C for HCF deviceThe Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

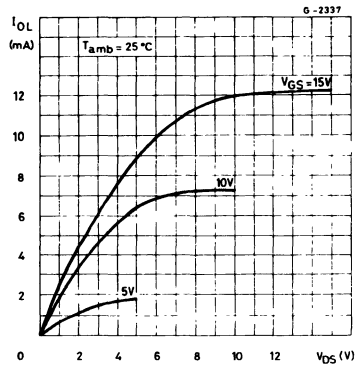
Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
t_{PLH} t_{PHL}	Propagation Delay Time (ϕ to Q4 out)		5		370	740	ns
			10		150	300	
			15		100	200	
t_{PLH} t_{PHL}	Propagation Delay Time (Q_n to Q_{n+1})		5		100	200	ns
			10		50	100	
			15		40	80	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_w	Input Pulse Width	$f = 100\text{ KHz}$	5		50	100	ns
			10		20	40	
			15		15	30	
t_r , t_f	Input Pulse Rise and Fall Time		5	Unlimited			μs
			10				
			15				
f_{max}	Maximum Clock Input Frequency		5	3.5	7		MHz
			10	8	16		
			15	12	24		
RESET OPERATION							
t_{PHL}	Propagation Delay Time		5		180	360	ns
			10		80	160	
			15		50	100	
t_w	Reset Pulse Width		5		60	120	ns
			10		30	60	
			15		20	40	
RC OPERATION							
	Variation of Frequency (Unit-to-Unit)	$C_X = 200\text{ pF}$ $R_S = 560\text{ K}\Omega$ $R_X = 50\text{ K}\Omega$	5	18	21.5	25	KHz
			10	20	23	26	
			15	21.1	24	27	
	Variation of Frequency With Voltage Change (Same Unit)	$C_X = 200\text{ pF}$ $R_S = 560\text{ K}\Omega$ $R_X = 50\text{ K}\Omega$	5 to 10			2	KHz
			10 to 15			1	
R_X		$C_X = 10\text{ }\mu\text{F}$	5			20	M Ω
			10			20	
			15			10	
C_X		$R_X = 500\text{ K}\Omega$	5			1000	mF
			10			50	
			15			50	
	Maximum Oscillator Frequency *	$R_X = 5\text{ K}\Omega$ $C_X = 15\text{ pF}$	10	530	650	810	pF
			15	690	800	94	

* RC oscillator applications are not recommended at supply voltages below 7V for $R_X = 50\text{ K}\Omega$

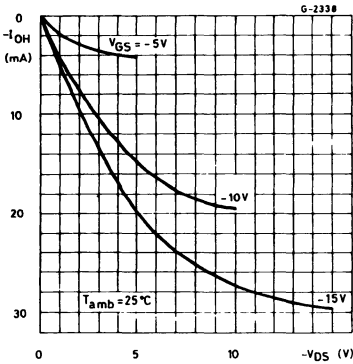
Typical Output Low (sink) Current Characteristics



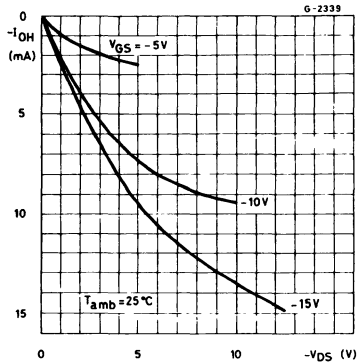
Minimum Output Low (sink) Current Characteristics



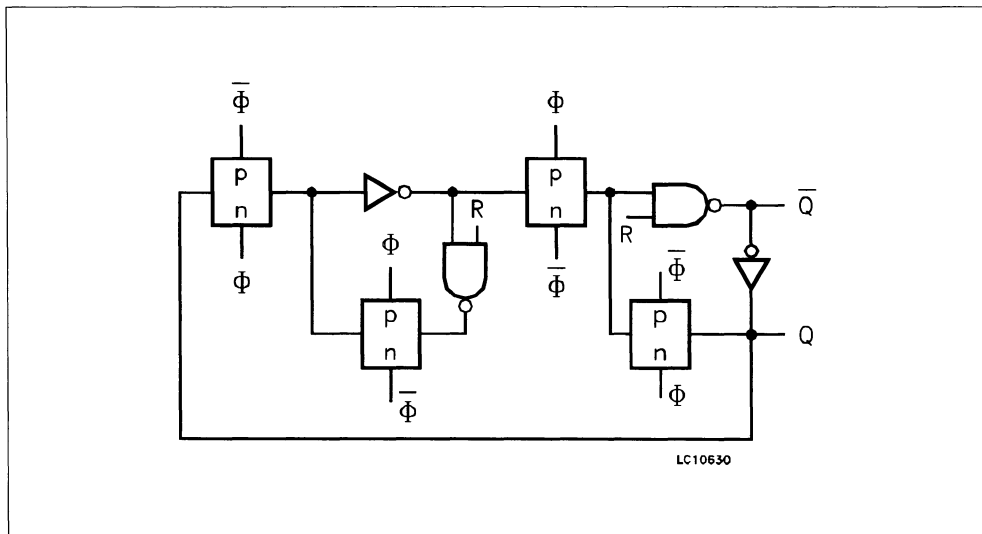
Typical Output High (source) Current Characteristics



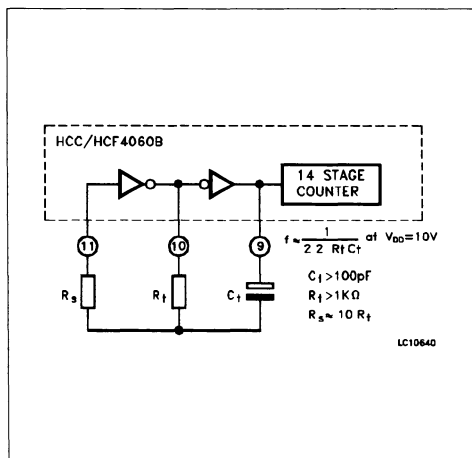
Minimum Output High (source) Current Characteristics



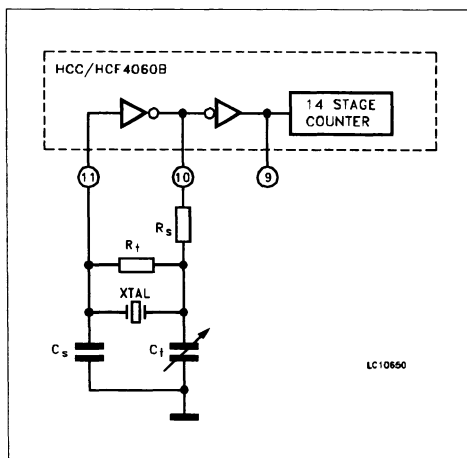
DETAIL OF TYPICAL FILP-FLOP STAGE



TYPICAL RC OSILLATOR CIRCUIT

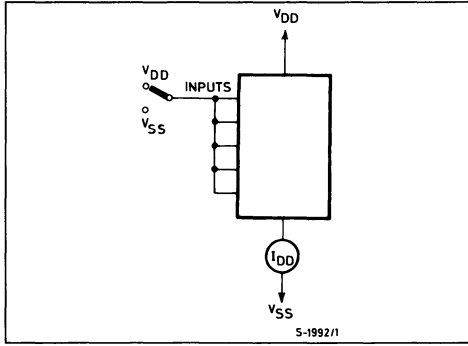


TYPICAL CRYSTAL OSCILLATOR CIRCUIT

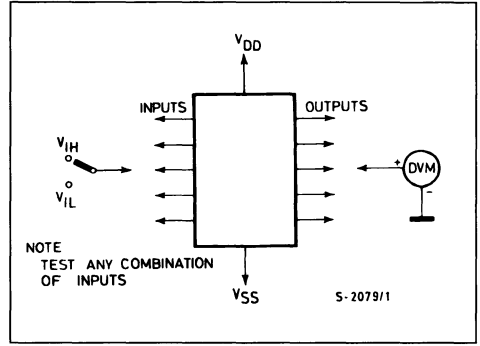


TEST CIRCUITS

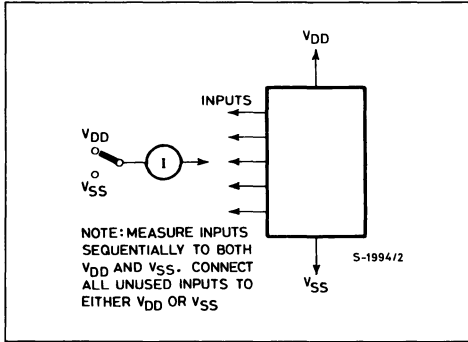
Quiescent Device Current.



Noise Immunity.

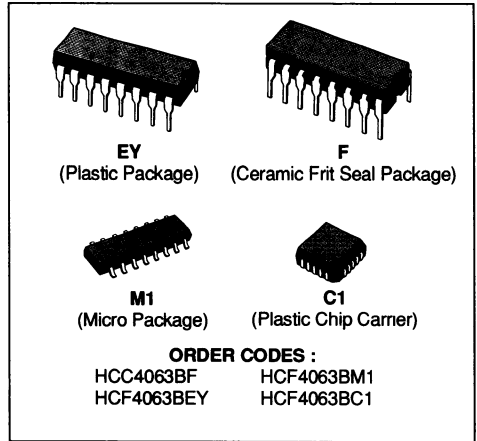


Input Leakage Current.



4-BIT MAGNITUDE COMPARATOR

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARD B-SERIES OUTPUT DRIVE
- EXPANSION TO 8-16V...4 N BITS BY CASCA-
DING UNITS
- MEDIUM SPEED OPERATION : COMPARES
TWO 4-BIT WORDS IN 250ns (typ.) AT 10V
- INPUT CURRENT OF 100nA AT 18V AND 25°C
FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TEN-
TATIVE STANDARD N° 13A, "STANDARD SPE-
CIFICATIONS FOR DESCRIPTION OF "B"
SERIES CMOS DEVICES"



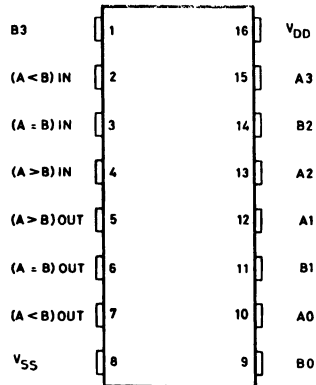
DESCRIPTION

The **HCC4063B** (extended temperature range) and **HCF4063B** (intermediate temperature range) are available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4063B** is a low-power 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to" or "greater than" a second 4-bit word. The **HCC/HCF4063B** has eight comparing inputs (A3, B3, through A0, B0), three outputs (A < B, A = B, A > B) and three cascading inputs (A < B, A = B, A > B) that permit systems designers to expand the comparator function to 8, 12, 16...4 N bits. When a single **HCC/HCF4063B** is used, the cascading inputs are connected as follows :

(A < B) = low, (A = B) = high, (A > B) = low.

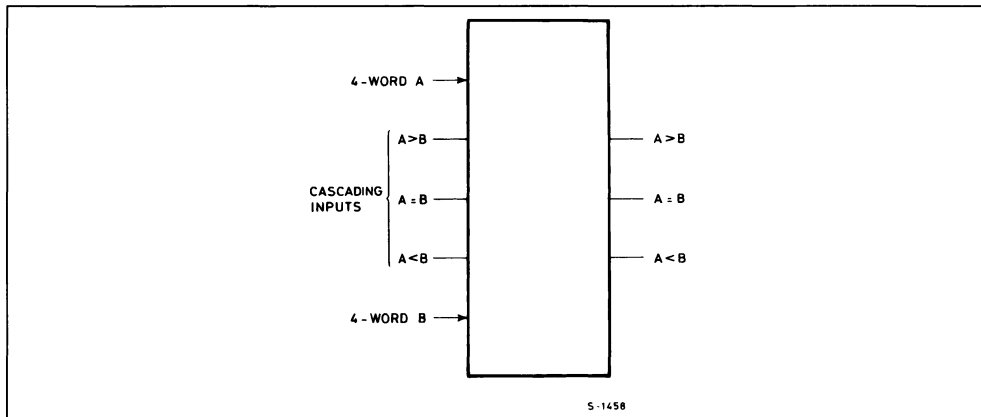
For words longer than 4 bits, **HCC/HCF4063B** devices may be cascaded by connecting the outputs of the less-significant comparator to the corresponding cascading inputs of the more-significant comparator. Cascading inputs (A < B, A = B, and A > B) on the least significant comparator are connected to a low, a high, and a low level, respectively.

PIN CONNECTIONS



5-1488/1

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

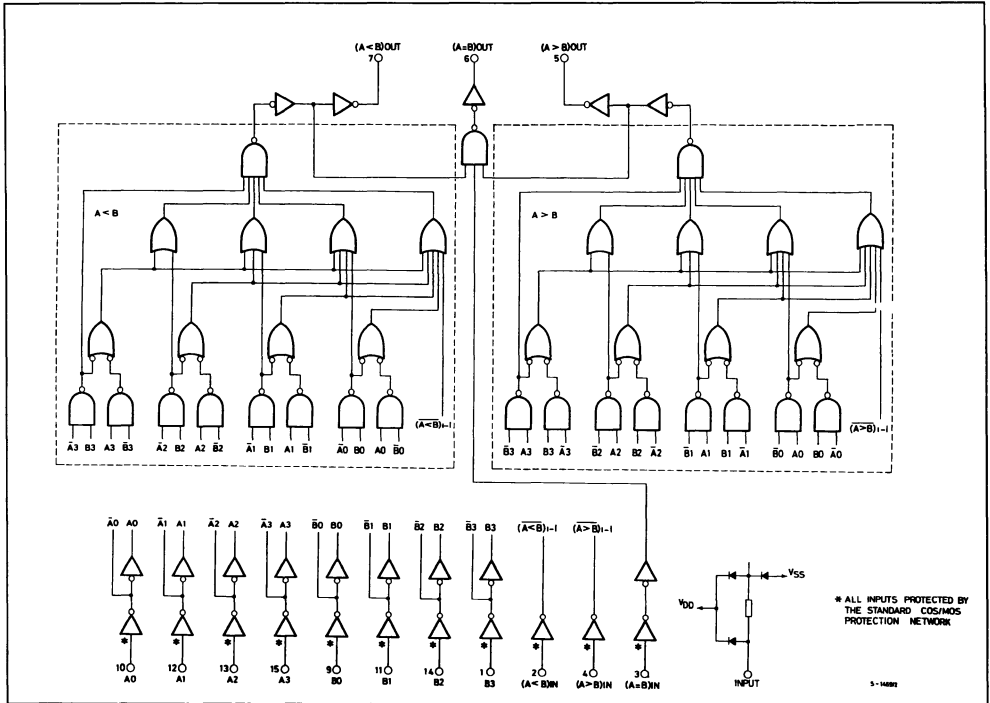
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$

LOGIC DIAGRAM



TRUTH TABLE

Inputs				Outputs					
Comparing				Cascading			Outputs		
A3, B3	A2, B2	A1, B1	A0, B0	A < B	A = B	A > B	A < B	A = B	A > B
A3 > B3	X	X	X	X	X	X	0	0	1
A3 = B3	A2 > B2	X	X	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 > B1	X	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	X	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	0	1	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	1	0	0	1	0
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	0	0	1	0	0
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	1	0	0
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	1	0	0
A3 = B3	A2 < B2	X	X	X	X	X	1	0	0
A3 < B3	X	X	X	X	X	X	1	0	0

X = Don't care

1 = High state

0 = Low state

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
		0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = - 55°C for HCC device . - 40°C for HCF device.

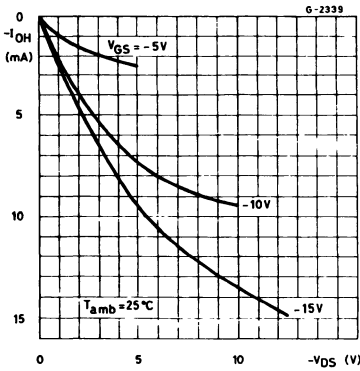
* T_{High} = + 125°C for HCC device . + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

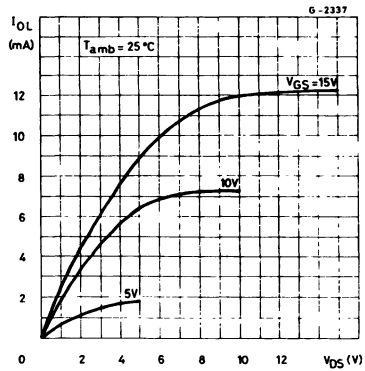
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time	Comparing Inputs to Outputs	5		625	1250	ns
			10		250	500	
			15		175	350	
		Cascading Inputs to Outputs	5		500	1000	
			10		200	400	
			15		140	280	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

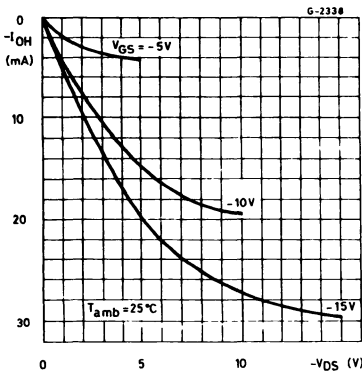
Minimum Output High (source) Current Characteristics.



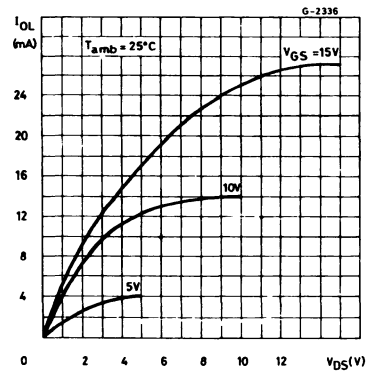
Minimum Output Low (sink) Current Characteristics.



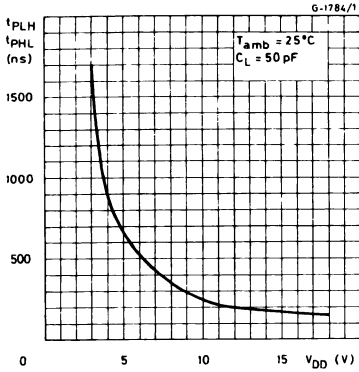
Typical Output High (source) Current Characteristics.



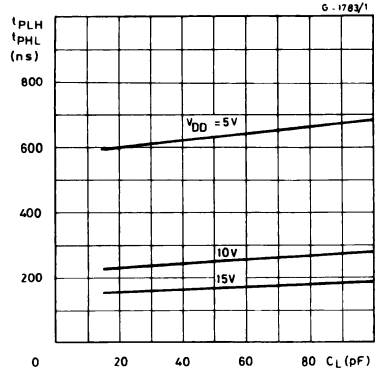
Typical Output Low (sink) Current Characteristics.



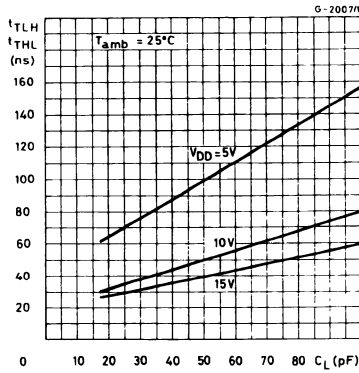
Typical Propagation Delay Time vs. V_{DD} .



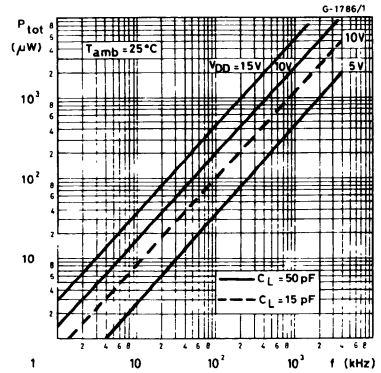
Typical Propagation Delay Time vs. C_L .



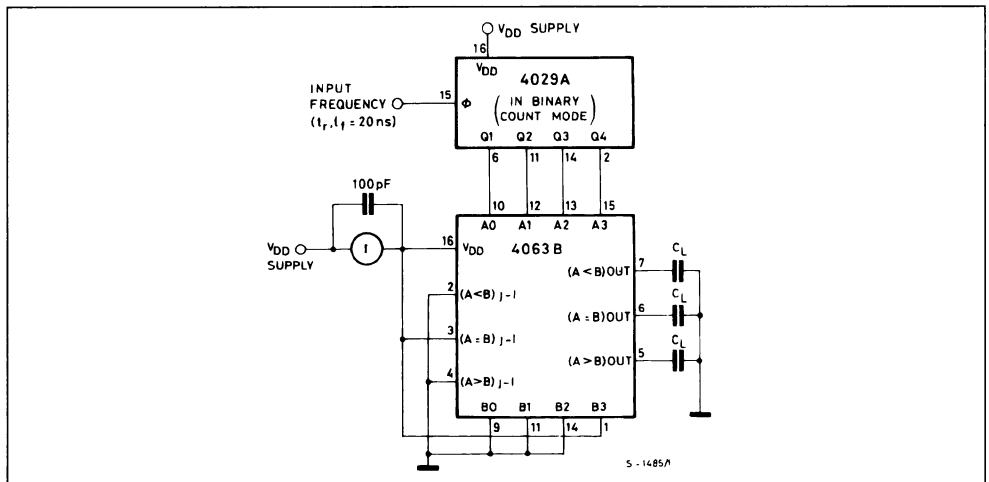
Typical Transition Time vs. Load Capacitance.



Typical Power Dissipation Characteristics.

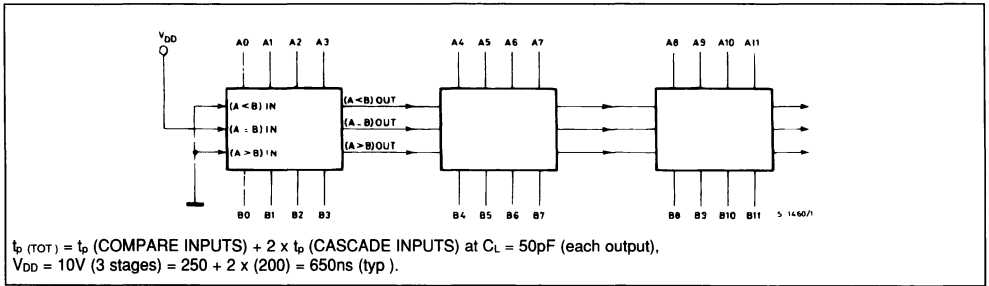


Dynamic Power Dissipation.



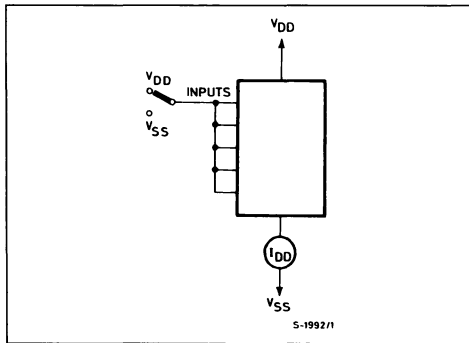
TYPICAL APPLICATION

TYPICAL SPEED CHARACTERISTICS OF A 12-BIT COMPARATOR

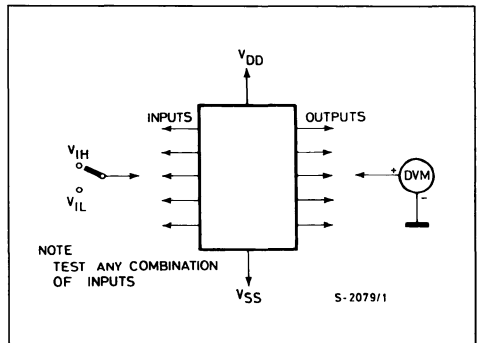


TEST CIRCUITS

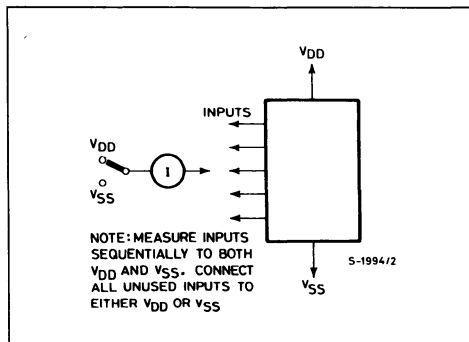
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.

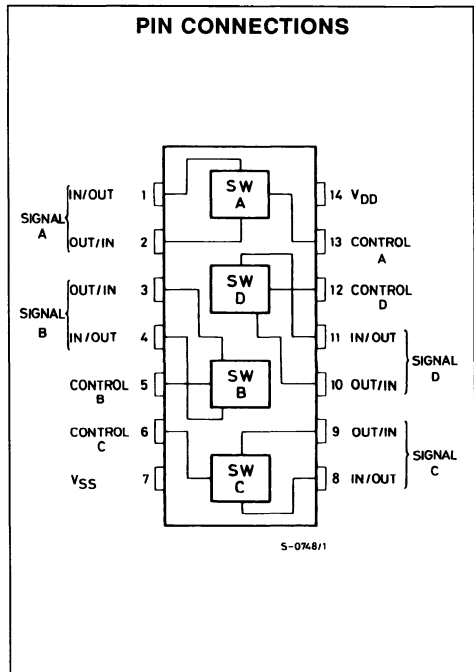
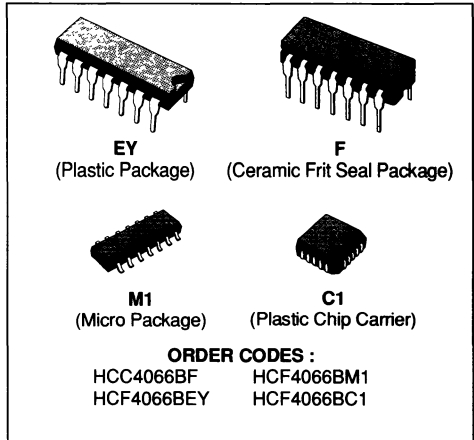


QUAD BILATERAL SWITCH FOR TRANSMISSION OR MULTIPLEXING OF ANALOG OR DIGITAL SIGNALS

- 15V DIGITAL OR $\pm 7.5V$ PEAK-TO-PEAK SWITCHING
- 80Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- SWITCH ON RESISTANCE MATCHED TO WITHIN 5Ω OVER 15V SIGNAL-INPUT RANGE
- ON RESISTANCE FLAT OVER FULL PEAK-TO-PEAK SIGNAL RANGE
- HIGH ON/OFF OUTPUT-VOLTAGE RATIO : $65dB$ TYP. @ $f_{is} = 10kHz$, $R_L = 10k\Omega$
- HIGH DEGREE OF LINEARITY : $< 0.5\%$ DISTORTION TYP. @ $f_{is} = 1kHz$, $V_{is} = 5V_{p-p}$, $V_{DD} - V_{SS} \geq 10V$, $R_L = 10k\Omega$
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE ; $10pA$ TYP. @ $V_{DD} - V_{SS} = 10V$, $T_A = 25^\circ C$
- EXTREMELY HIGH CONTROL INPUT IMPEDANCE (control circuit isolated from signal circuit) : $10^{12}\Omega$ TYP.
- LOW CROSSTALK BETWEEN SWITCHES : $-50dB$ TYP. @ $f_{is} = 0.9MHz$, $R_L = 1k\Omega$
- MATCHED CONTROL-INPUT TO SIGNAL-OUTPUT CAPACITANCE : REDUCES OUTPUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE, SWITCH ON = $40MHz$ (typ.)
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF $100nA$ AT 18V AND $25^\circ C$ FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4066B** (extended temperature range) and **HCF4066B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4066B** is a quad bilateral switch intended for the transmission or multiplexing of analog or digital signals. It is pin-for-pin

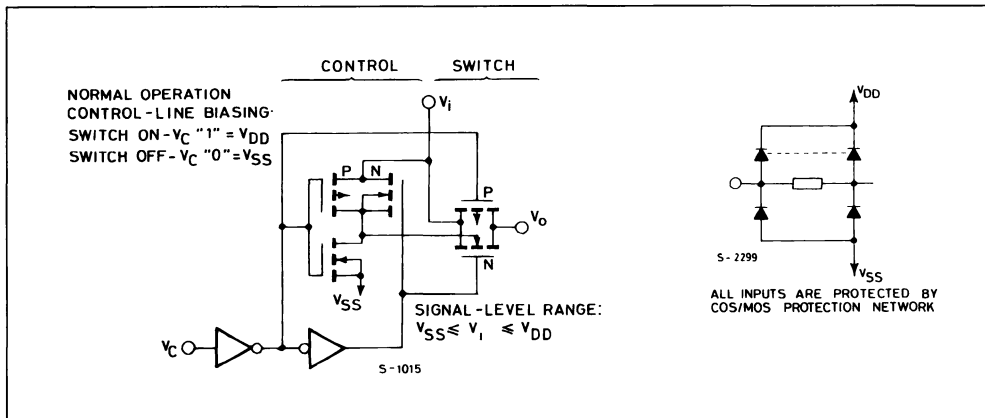


compatible with **HCC/HCF4016B**, but exhibits a much lower ON resistance. In addition, the ON resistance is relatively constant over the full input-signal range. The **HCC/HCF4066B** consists of four independent bilateral switches. A single control signal is required per switch. Both the p and the n device in a given switch are biased ON or OFF simultaneously by the control signal. As shown in schematic diagram, the well of the n-channel device on each switch is either tied to the input when the switch is ON or to V_{SS} when the switch is OFF. This configura-

tion eliminates the variation of the switch-transistor threshold voltage with input signal, and thus keeps the ON resistance low over the full operating-signal range. The advantages over single-channel switches include peak input signal voltage swings equal to the full supply voltage, and more constant ON impedance over the input-signal range. For sample-and-hold applications, however, the **HCC/HCF4016B** is recommended.

SCHEMATIC DIAGRAM

1 OF 4 IDENTICAL SWITCHES AND ITS ASSOCIATED CONTROL CIRCUITRY.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200	mW
		100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

ELECTRICAL CHARACTERISTICS

(T_{amb} = 25°C, typical temperature coefficient for all V_{DD} values is 0,3%/°C)

Symbol	Parameter		Test Conditions				Value				Unit
			V _I (V)	V _{DD} (V)	T _{Low} *		25°C		T _{High} *		
					Min.	Max.	Min.	Typ.	Max.	Min.	
I _L	Quiescent Device Current (all switches ON or all switches OFF)	HCC Types	0/ 5	5		0.25	0.01	0.25		7.5	µA
			0/10	10		0.5	0.01	0.5		15	
			0/15	15		1	0.01	1		30	
			0/20	20		5	0.02	5		150	
		HCF Types	0/ 5	5		1	0.01	1		7.5	
			0/10	10		2	0.01	2		15	
			0/15	15		4	0.01	4		30	

SIGNAL INPUTS (V_{is}) and Outputs (V_{os})

R _{ON}	On Resistance	HCC Types	V _C = V _{DD} R _L = 10kΩ Return to V _{DD} - V _{SS} 2 V _{is} = V _{SS} to V _{DD}	5	800	470	1050	1300	Ω
				10	310	180	400	550	
				15	200	125	240	320	
		HCF Types		5	850	470	1050	1200	
				10	330	180	400	500	
		15	210	125	240	300			
ΔON	Resistance between any 2 Switches, ΔR _{ON}	R _L 10kΩ, V _C = V _{DD}	5		15			Ω	
			10		10				
			15		5				
TDH	Total Harmonic Distorsion	V _C = V _{DD} = 5V, V _{SS} = - 5V, V _{is} (p-p) = 5V (sine wave centered in 0V) R _L = 10kΩ, f _{is} = 1kHz sine wave			0.4			%	
	- 3 dB Cutoff Frequency (switch on)	V _C = V _{DD} = 5V, V _{SS} = - 5V, V _{is} (p-p) = 5V (sine wave centured on 0V) R _L = 1kΩ			40			MHz	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device : + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value						Unit	
			V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
				Min.	Max.	Min.	Typ.	Max.	Min.		Max.
	- 50 dB Feedthrough Frequency (switch off)	V _C = V _{SS} = - 5V, V _{is} (p-p) = 5V (sine wave centured on 0V) R _L = 1kΩ					1				MHz
	- 50 dB Crosstalk Frequency	V _C (A) = V _{DD} = + 5V V _C (B) = V _{SS} = - 5V V _{is} (A) = 5Vp-p, 50Ω source R _L = 1kΩ					8				MHz
t _{pd}	Propagation Delay (signal input to signal output)	R _L = 200kΩ V _C = V _{DD} , V _{SS} = GND, C _L = 50pF, V _{is} = 10V (square wave centured on 5V) t _r , t _f = 20ns		5			20	40			ns
				10			10	20			
				15			7	15			
C _{is}	Input Capacitance	V _{DD} = + 5V V _C = V _{SS} = - 5V					8			pF	
C _{os}	Output Capacitance						8				
C _{ios}	Feedthrough						0.5				
	Input/Output Leakage Current Switch OFF	HCC Types	V _C = 0V V _{is} = 18V, V _{os} = 0V V _{is} = 0V; V _{os} = 18V	18		± 0.1	±10 ⁻³	± 0.1		± 1	μA
		HCF Types	V _C = 0V V _{is} = 15V, V _{os} = 0V V _{is} = 0V, V _{os} = 15V	15		± 0.3	±10 ⁻³	± 0.3		± 1	
CONTROL (V_C)											
V _{ILC}	Control Input Low Voltage	I _{is} < 10μA V _{is} = V _{SS} , V _{os} = V _{DD} and V _{is} = V _{DD} , V _{os} = V _{SS}		5		1		1		1	V
				10		2		2		2	
				15		2		2		2	
V _{IHC}	Control Input High Voltage			5	3.5		3.5		3.5		V
				10	7		7		7		
				15	11		11		11		
I _{HI} , I _{IL}	Input Leakage Current	HCC Types	V _{is} ≤ V _{DD} V _{DD} - V _{SS} = 18V	18		± 0.1	±10 ⁻⁵	± 0.1		± 1	μA
		HCF Types	V _{DD} - V _{SS} = 15V V _{CC} ≤ V _{DD} - V _{SS}	15		± 0.3	±10 ⁻⁵	± 0.3		± 1	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device.

* T_{High} = + 125°C for HCC device + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions	Value						Unit		
			V _{DD} (V)	T _{Low} *		25°C				T _{High} *	
				Min.	Max.	Min.	Typ.	Max.		Min.	Max.
	Crosstalk (control input to signal output)	V _C = 10V (sq. wave) t _r , t _f = 20ns R _L = 10kΩ	10			50					mV
	Turn-on Propagation Delay	V _{IN} = V _{DD} t _r , t _f = 20ns C _L = 50pF R _L = 1kΩ	5			35	70				ns
			10			20	40				
			15			15	30				
	Control Input Repetition Rate	V _{IS} = V _{DD} , V _{SS} = GND R _L = 1kΩ to gnd C _L = 50pF V _C = 10V (square wave centured on 5V) t _r , t _f = 20ns V _{os} = 1/2V _{os} @ 1kHz	5			6					MHz
			10			9					
			15			9.5					
C _I	Input Capacitance	Any Input				5	7.5				pF

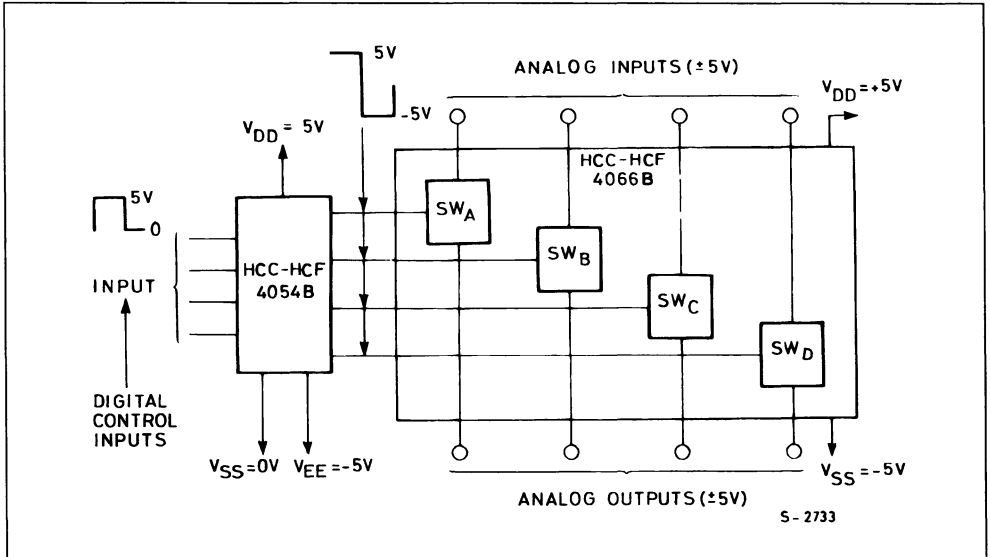
* T_{Low} = - 55°C for HCC device - 40°C for HCF device

* T_{High} = + 125°C for HCC device + 85°C for HCF device

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

TYPICAL APPLICATIONS

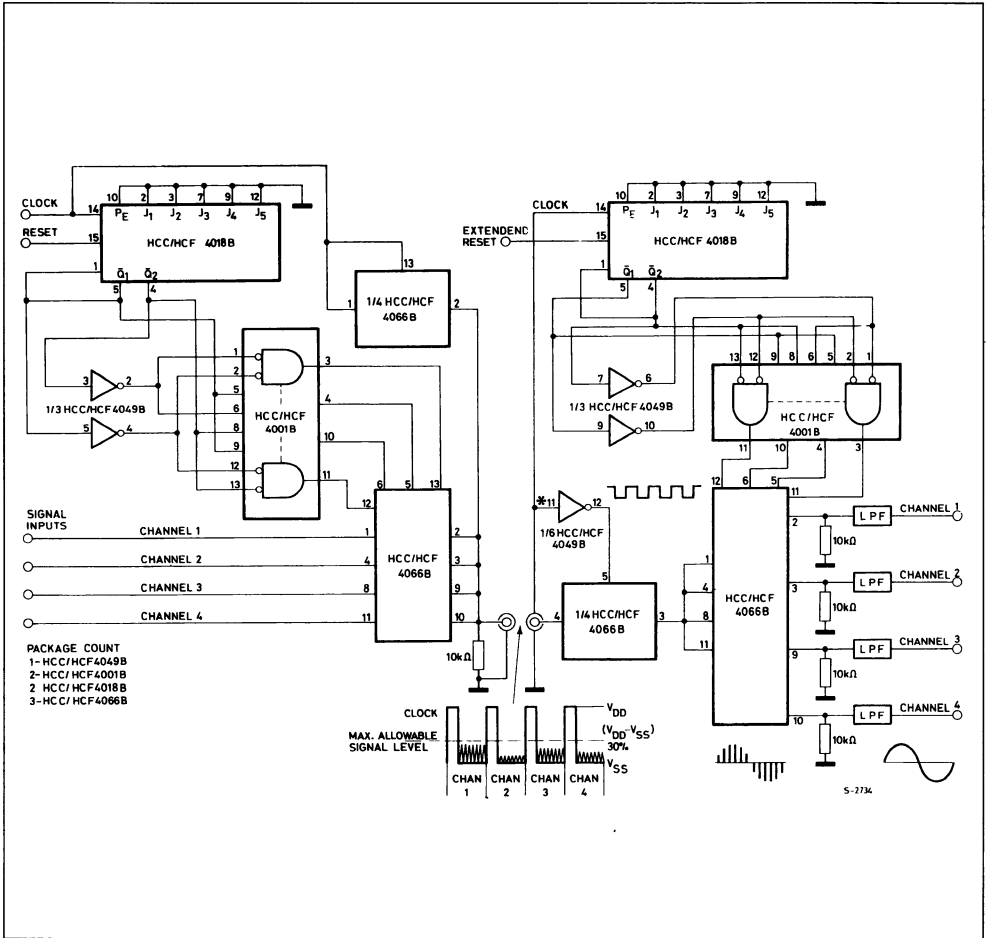
BIDIRECTIONAL SIGNAL TRANSMISSION VIA DIGITAL CONTROL LOGIC



S- 2733

TYPICAL APPLICATIONS (continued)

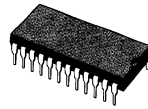
4-CHANNEL PAM MULTIPLEX SYSTEM DIAGRAM.



ANALOG MULTIPLEXER/DEMULTIPLEXER

4067B—SINGLE 16-CHANNEL
4097B—DIFFERENTIAL 8-CHANNEL

- **LOW ON RESISTANCE:** 125Ω (typ.) OVER 15 V_{p-p} SIGNAL INPUT RANGE FOR V_{DD} - V_{SS} = 15V
- **HIGH OFF RESISTANCE:** CHANNEL LEAKAGE OF ±10pA (typ.) @ V_{DD} - V_{SS} = 10V
- **MATCHED SWITCH CHARACTERISTICS:** ΔR_{ON} = 5Ω (typ.) FOR V_{DD} - V_{SS} = 15V
- **VERY LOW QUIESCENT POWER DISSIPATION** UNDER A DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS: 0.2μW (typ.) @ V_{DD} - V_{SS} = 10V
- **BINARY ADDRESS DECODING ON CHIP**
- **QUIESCENT CURRENT** SPECIFIED TO 20V FOR HCC DEVICE
- **STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS**
- **5V, 10V AND 15V PARAMETRIC RATINGS**
- **INPUT CURRENT** OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- **100% TESTED FOR QUIESCENT CURRENT**
- **MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIE CMOS DEVICES"**


EY
 (Plastic Package)

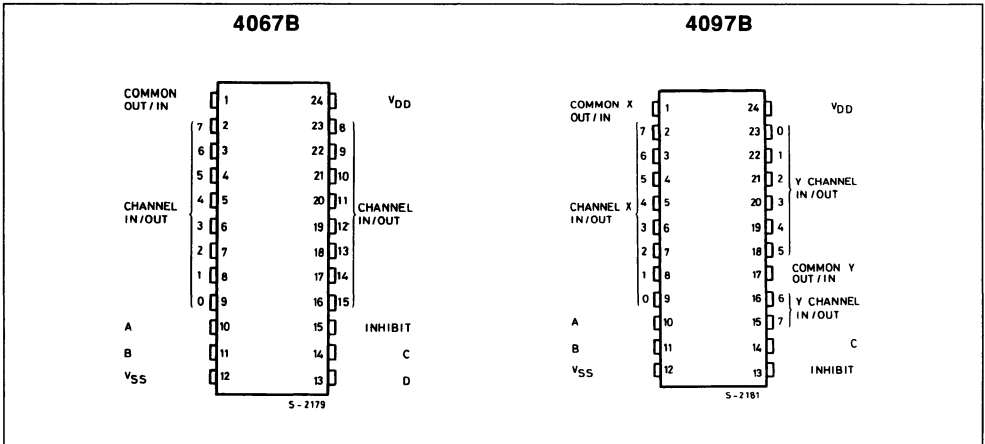
F
 (Ceramic Package)

M1
 (Micro Package)

C1
 (Chip Carrier)

ORDER CODES :

HCC40XXBF	HCF40XXBM1
HCF40XXBEY	HCF40XXBC1

PIN CONNECTIONS


DESCRIPTION

The **HCC4067B**, **HCC4097B** (extended temperature range) and **HCF4067B**, **HCF4097B** (intermediate temperature range) are monolithic integrated circuits available in 24-lead dual in line plastic or ceramic package.

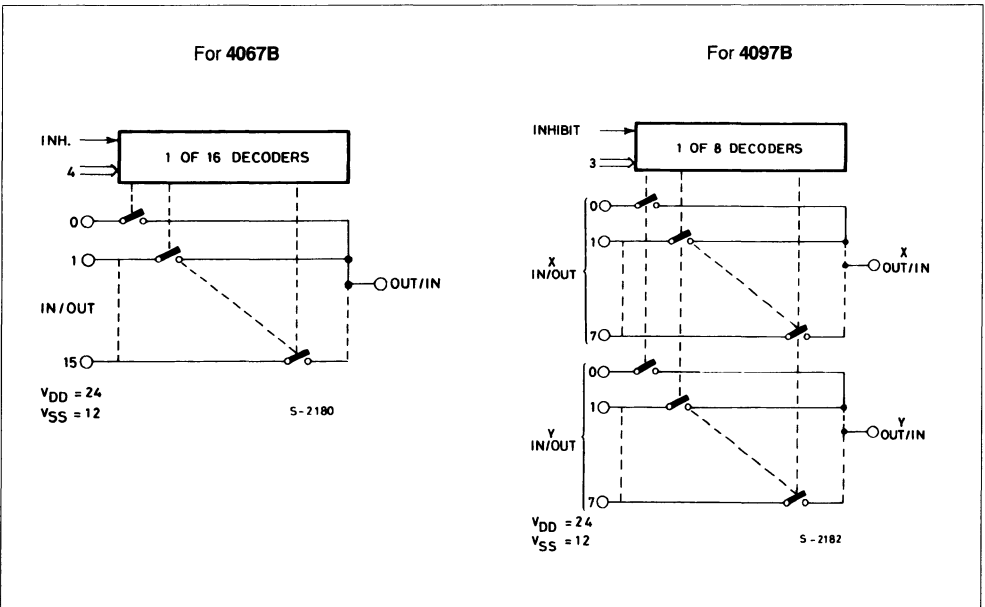
The **HCC/HCF4067B** and **HCC/HCF4097B** COS/MOS analog multiplexers/demultiplexers are digitally controlled analog switches having low ON impedance, low OFF leakage current and internal address decoding. In addition, the ON resistance is

relatively constant over the full input-signal range.

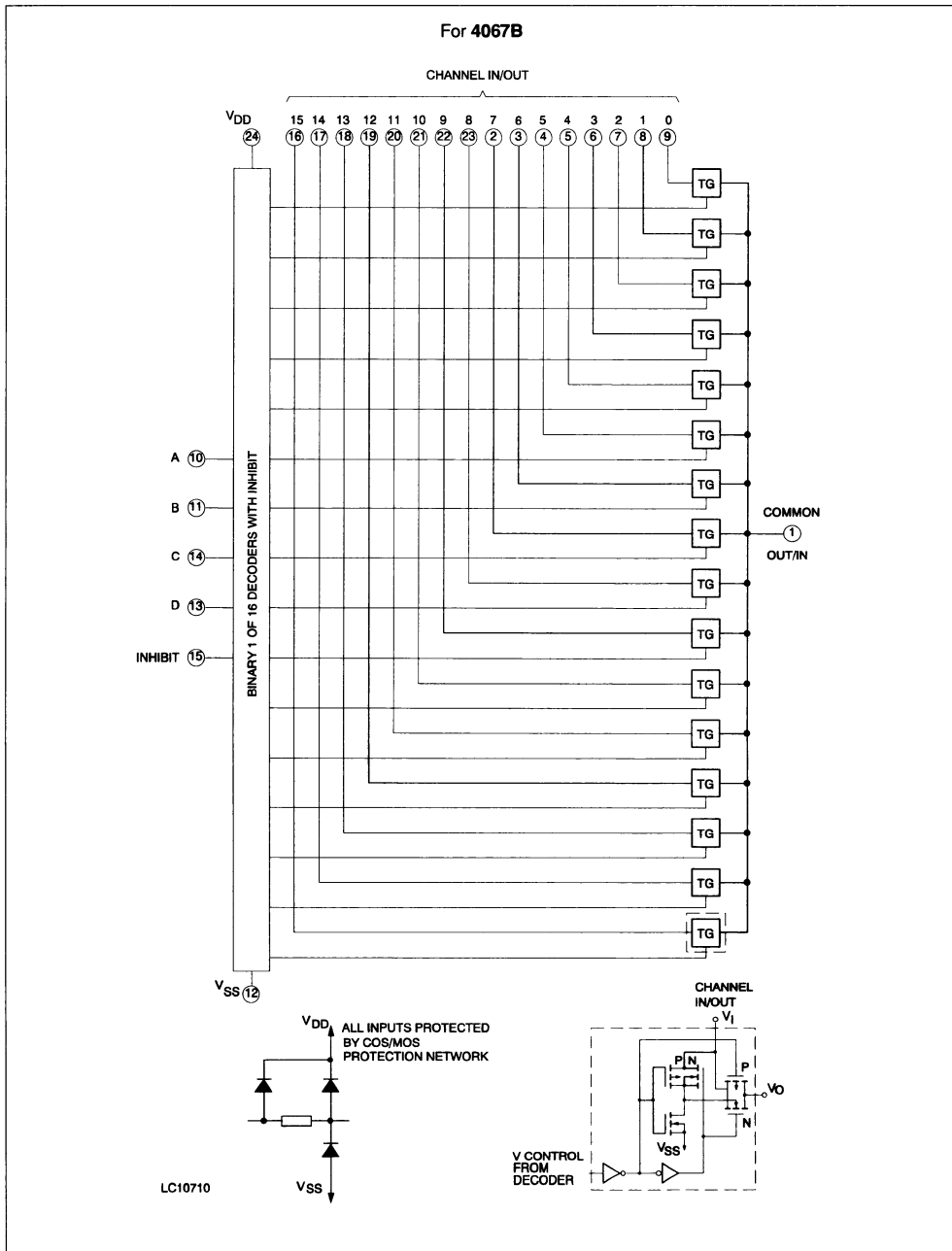
The **HCC/HCF4067B** is a 16-channel multiplexer with four binary control inputs A, B, C, D, and an inhibit input, arranged so that any combination of the inputs selects one switch.

The **HCC/HCF4097** is a differential 8-channel multiplexer having three binary control inputs A, B, C, and an inhibit input. The inputs permit selection of one of eight pairs of switches. A logic "1" present at the inhibit input turn all channels off.

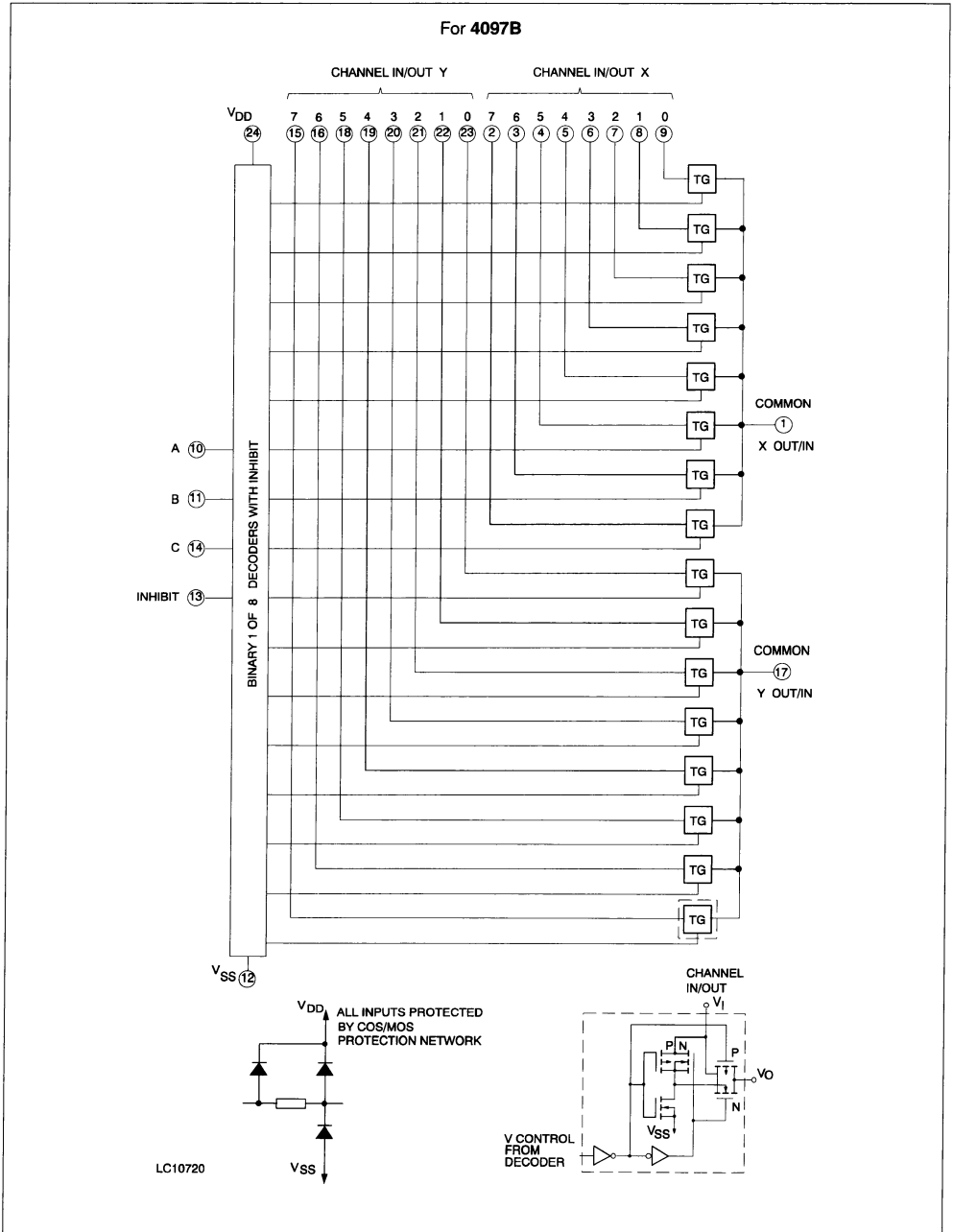
FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



LOGIC DIAGRAM



TRUTH TABLES FOR HCC/HCF4067B

A	B	C	D	INH	SELECTED CHANNEL
X	X	X	X	1	None
0	0	0	0	0	0
1	0	0	0	0	1
0	1	0	0	0	2
1	1	0	0	0	3
0	0	1	0	0	4
1	0	1	0	0	5
0	1	1	0	0	6
1	1	1	0	0	7
0	0	0	1	0	8
1	0	0	1	0	9
0	1	0	1	0	10
1	1	0	1	0	11
0	0	1	1	0	12
1	0	1	1	0	13
0	1	1	1	0	14
1	1	1	1	0	15

TRUTH TABLE FOR HCC/HCF4097B

A	B	C	INH	SELECTED CHANNEL
X	X	X	1	None
0	0	0	0	0X 0Y
1	0	0	0	1X 1Y
0	1	0	0	2X 2Y
1	1	0	0	3X 3Y
0	0	1	0	4X 4Y
1	0	1	0	5X 5Y
0	1	1	0	6X 6Y
1	1	1	0	7X 7Y

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
V_i	Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	$^{\circ}C$ $^{\circ}C$

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit										
			V _{IS} (V)	V _{EE} (V)	V _{SS} (V)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *											
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.									
I _L	Quiescent Supply Current	HCC types	0	0	0	5		5		0.04	5		150										
						10		0.04	10		300												
						15		0.04	20		600												
						20		0.08	100		3000												
		HCF types				5		0.04	20		150												
						10		0.04	40		300												
			15		0.04	80		0.04	80		600												
SWITCH																							
R _{ON}	On Resistance	HCC types	0 ≤ V _I ≤ V _{DD}	0	0	5		800		470	1050		1300										
						10		310		180	400		580										
						15		200		125	240		320										
						5		850		470	1050		1200										
		HCF types				10		330		180	400		520										
						15		210		125	240		300										
ΔON	Resistance ΔR _{ON} (Between any two channels)			0	0	5				10													
						10				10													
						15				5													
OFF (*) Channel Leakage Current	Any Channel OFF	HCC types	0	0	18	100		±0.1	100			1000											
													HCF types	0	0	15	300	±0.1	300		1000		
		HCC types																				0	0
													HCF types	0	0	15	300	±0.1	300		1000		
C	Capacitance Input Output for 4067 Output for 4097 Feedthrough			-5	5				5			pF											
																					55		
									0.2														
													CONTROL										
V _{IL}	Input Low Voltage		= V _{DD} thru 1KΩ	V _{EE} =V _{SS} R _L = 1KΩ to V _{SS} I _{IS} < 2μA (on all OFF channels)	5		1.5			1.5		1.5											
					10		3			3		3											
					15		4			4		4											
V _{IH}	Input High Voltage				5	3.5		3.5				3.5											
					10	7		7			7												
					15	11		11			11												
I _{IH} I _{IL}	Input Leakage Current	HCC types	V _I = 0/18V		18		±0.1		±10 ⁻³	±0.1		±1											
		HCF types											V _I = 0/15V	15		±0.3		±10 ⁻³	±0.3		±1		
C _I	Input Capacitance		Any Address or Inhibit Input						5	7.5		pF											





* Determined by minimum feasible leakage measurement for automatic testing

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

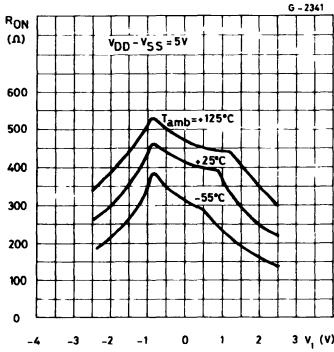
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions							Value		Unit		
		V_C (V)	R_L (K Ω)	f_i (KHz)	V_i (V)	V_{SS} (V)	V_{DD} (V)	Typ.	Max.				
SWITCH													
t_{pd}	Propagation Delay Time (Signal Input to Output)	$= V_{DD}$	200		0	5			30	60	ns		
						10			15	30			
						15			11	20			
	Frequency Response Channel "ON" (Sine Wave Input) at $20\text{ Log } \frac{V_O}{V_I} = -3\text{ dB}$	$= V_{DD}$	1	5 (*)	0	10			V_O at Common OUT/IN	4067B	14	ns	
										4097B	20		
									V_O at Any Channel		60		
	Feedthrough (All Channels OFF) at $20\text{ Log } \frac{V_O}{V_I} = -40\text{ dB}$	$= V_{SS}$	1	5 (*)	0	10			V_O at Common OUT/IN	4067B	20	MHz	
										4097B	12		
									V_O at Any Channel		8		
	Frequency Signal Crosstalk at $20\text{ Log } \frac{V_{\alpha\beta}}{V_{\kappa\alpha}} = -40\text{ dB}$	$V_{C(A)}=V_{DD}$ $V_{C(B)}=V_{SS}$	1	5 (*)	0	10			Between Any two (A and B) Channels		1	MHz	
									V_O at Any Channel	Measured on common	10		
										Measured on Any Channel	18		
t_w	Sine Wave Distortion ($f_s = 1\text{ KHz}$ sine wave)	5	10	1	2 (*)	0	5			0.3	%		
		10	10	1	3 (*)	0	10			0.2			
		15	10	1	5 (*)	0	15			0.12			
CONTROL (address or Inhibit)													
t_{PLH} t_{PHL}	Propagation Delay Time: Address or Inhibit to Signal OUT (Channel Turning ON)		1						0	5	325	650	ns
0									10	135	270		
0									15	95	190		
t_{PLH} t_{PHL}	Propagation Delay Time: Address or Inhibit to Signal OUT (Channel Turning OFF)		0.3						0	5	220	440	ns
0									10	90	180		
0									15	65	130		
	Address or Inhibit to Signal Crosstalk		10*						0	10	75		mV peak

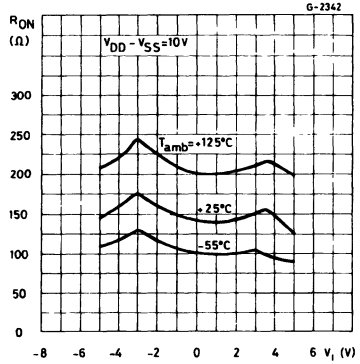
(*) Peak to peak voltage symmetrical about $\frac{V_{DD} - V_{SS}}{2}$

(*) Both ends of channel

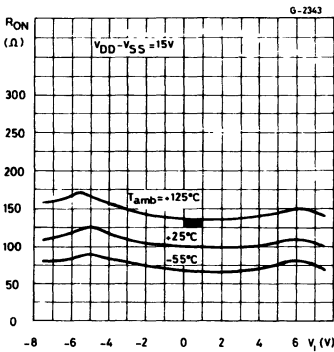
Typical ON Resistance vs Input Signal Voltage (All Types)



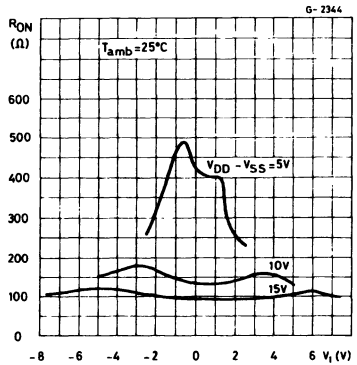
Typical ON Resistance vs Input Signal Voltage (All Types)



Typical ON Resistance vs Input Signal Voltage (All Types)

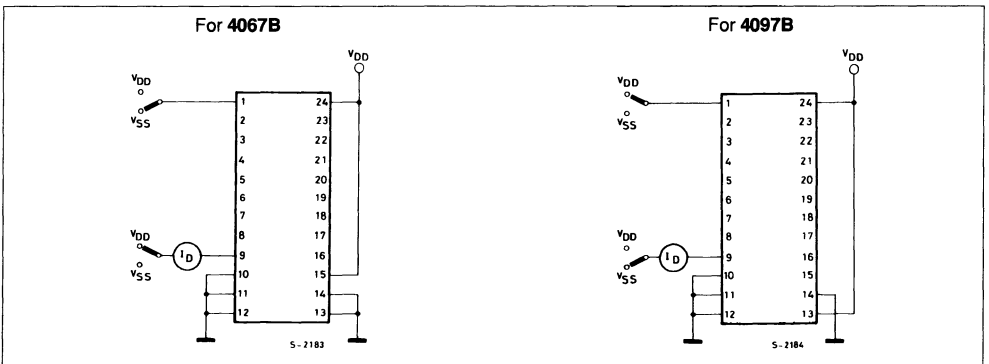


Typical ON Resistance vs Input Signal Voltage (All Types)

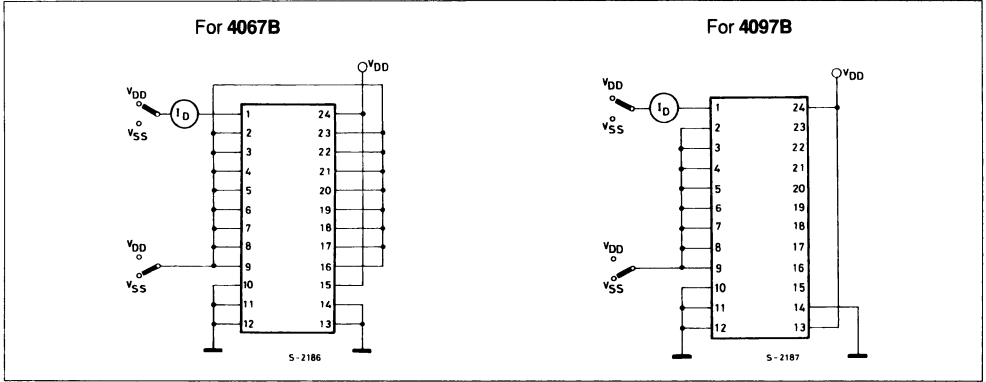


TEST CIRCUITS

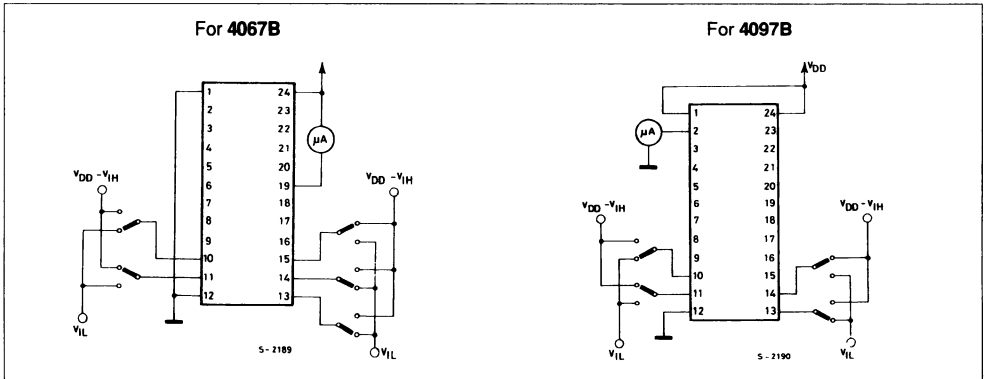
OFF Channel Leakage Current Any Channel OFF



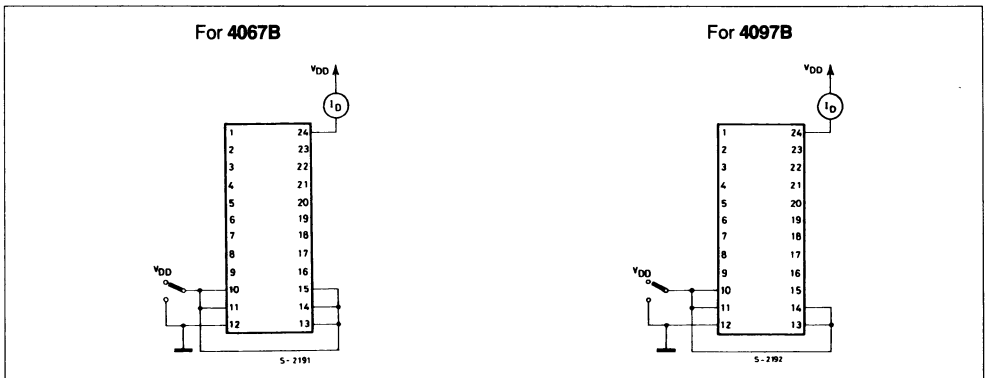
OFF Channel Leakage Current All Channels OFF



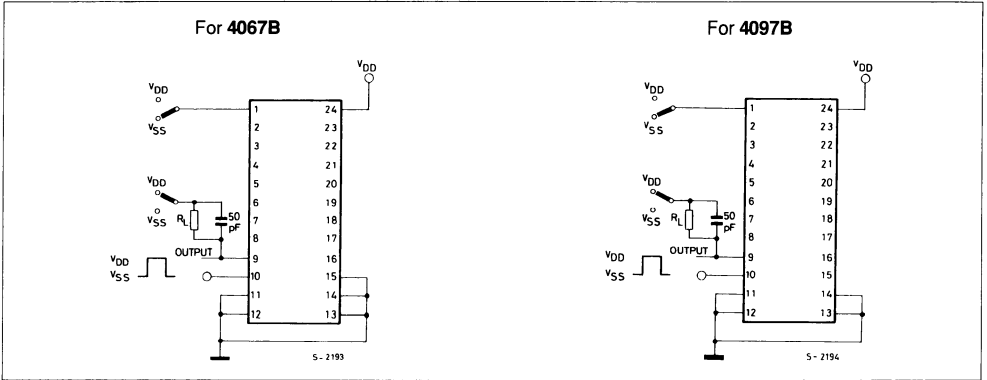
Input Voltage Measure < 2 μ A an All OFF Channels (e.g. Channel 12)



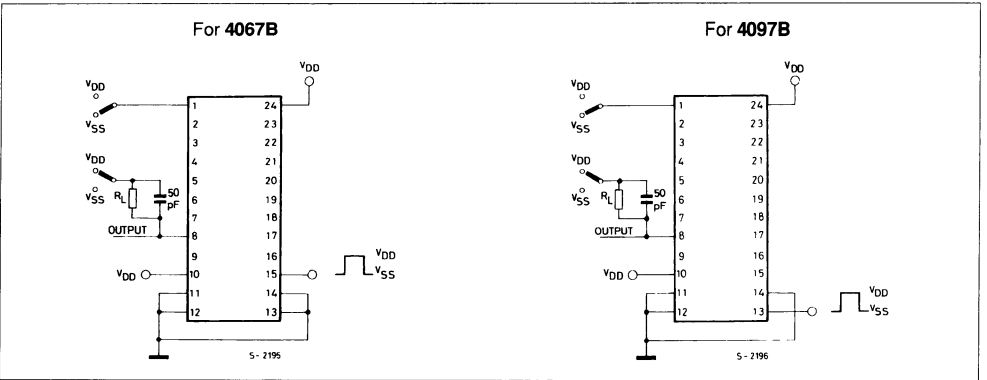
Quiescent Device Current



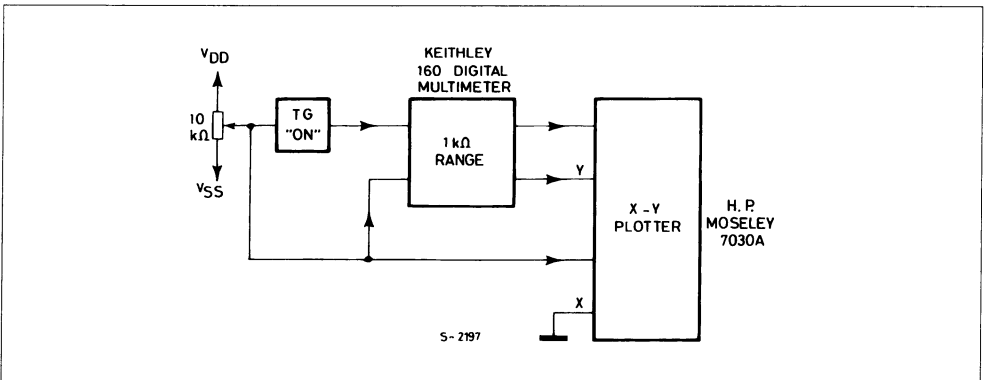
Turn-on and Turn-off Propagation Delay Address Select Input to Signal Output (e. g. Channel 0)



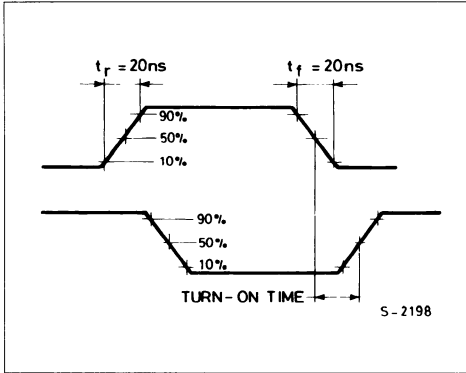
Turn-on and Turn-off Propagation Delay-Inhibit Input to Signal Output (e. g. Channel 1)



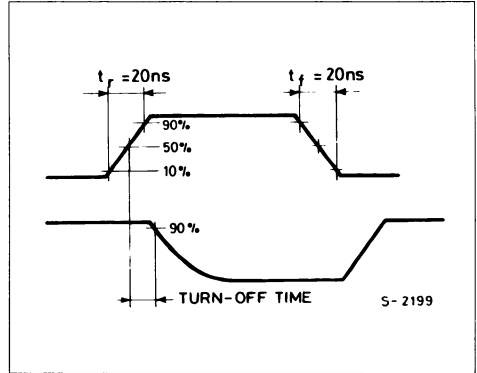
Channel ON Resistance Measurement Circuit



Propagation Delay Waveform Channel Being Turned ON ($R_L = 10\text{ K}\Omega$, $C_L = 50\text{ pF}$)



Propagation Delay Waveform Channel Being Turned OFF ($R_L = 300\ \Omega$, $C_L = 50\text{ pF}$)



APPLICATIONS INFORMATION

In applications where separate power sources are used to drive V_{DD} and the signal inputs, the V_{DD} current capability should exceed V_{DD}/R_L ($R_L =$ effective external load). This provision avoids permanent current flow or clamp action on the V_{DD} supply when power is applied or removed from the **HCC/HCF4067B** or **HCC/HCF4097B**.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned ON or OFF by an address input, there is a momentary conductive path from the channel to V_{SS} , which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to V_{SS} .

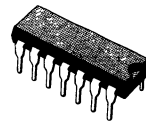
The amount of charge dumped is mostly a function of the signal level above V_{SS} . Typically, at $V_{DD} - V_{SS} = 10\text{V}$, a 100 pF capacitor connected to the input or output of the channel will

lose 3-4% of its voltage at the moment the channel turns ON or OFF. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1-2 μs . When the inhibit signal turns a channel off, there is no charge dumping of V_{SS} . Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to the capacitance coupling from inhibit input to channel input or output. Address input also couple some voltage steps onto the channel signal levels.

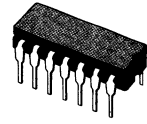
In certain applications, the external load-resistor current may include both V_{DD} and signal line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 V (calculated from R_{ON} values shown in ELECTRICAL CHARACTERISTICS CHART). No V_{DD} current will flow through R_L if the switch current flows into terminal 1 on the **HCC/HCF4067B**, terminals 1 and 17 on the **HCC/HCF4097B**.

8-INPUT NAND/AND GATE

- MEDIUM-SPEED OPERATION — t_{PHL} , t_{PLH} = 75ns (typ.) AT 10V
- BUFFERED OUTPUT
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)



C1
(Plastic Chip Carrier)

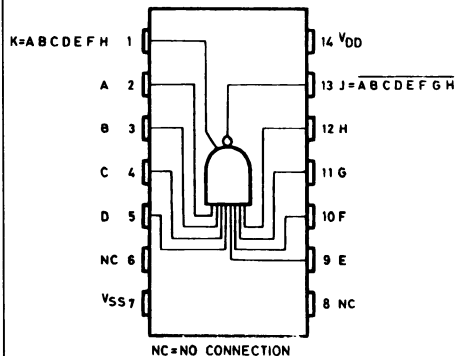
ORDER CODES :

HCC4068BF HCF4068BM1
HCF4068BEY HCF4068BC1

DESCRIPTION

The **HCC4068B** (extended temperature range) and **HCF4068B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4068B** NAND/AND gate provides the system designer with direct implementation of the positive-logic 8-input NAND and AND functions and supplements the existing family of COS/MOS gates.

PIN CONNECTIONS



NC=NO CONNECTION

5 1823/3

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to 125	°C
		- 40 to 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (µA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		0.25	0.01	0.25		7.5	µA
			0/10			10		0.5	0.01	0.5		15	
			0/15			15		1	0.01	1		30	
			0/20			20		5	0.02	5		150	
		HCF Types	0/ 5			5		1	0.01	1		7.5	
			0/10			10		2	0.01	2		15	
			0/15			15		4	0.01	4		30	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95	V	
		0/10		< 1	10	9.95		9.95			9.95		
		0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05	0.05	V	
		10/0		< 1	10		0.05			0.05	0.05		
		15/0		< 1	15		0.05			0.05	0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V	
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		

* T_{Low} = - 55°C for **HCC** device ; - 40°C for **HCF** device.

* T_{High} = + 125°C for **HCC** device ; + 85°C for **HCF** device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

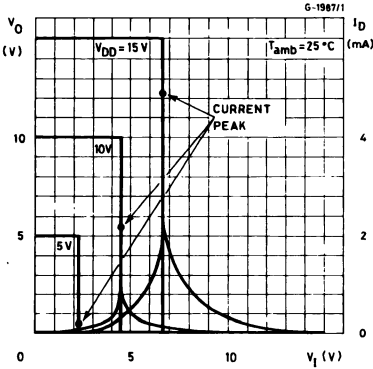
Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36	
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9	
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1	
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36	
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9			
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

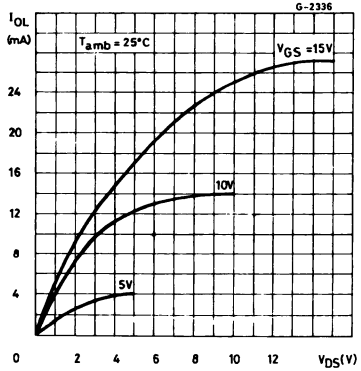
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PHL} , t _{PLH}	Propagation Delay Time		5		150	300	ns
			10		75	150	
			15		55	110	
t _{TLH} , t _{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

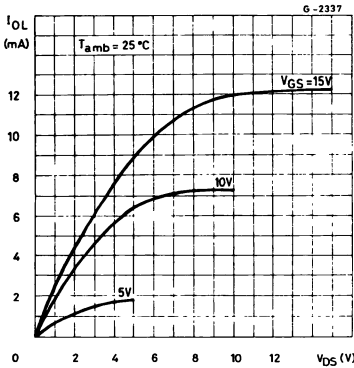
Typical Voltage and Current Transfer Characteristics.



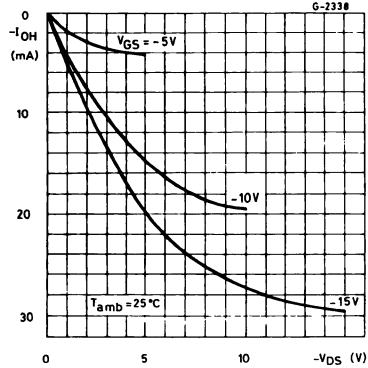
Typical Output Low (sink) Current Characteristics.



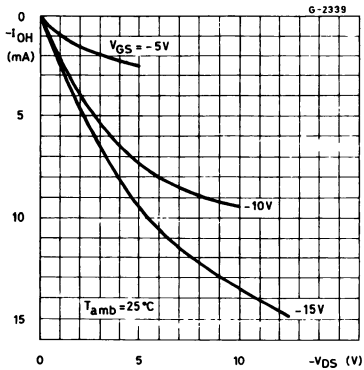
Minimum Output Low (sink) Current Characteristics.



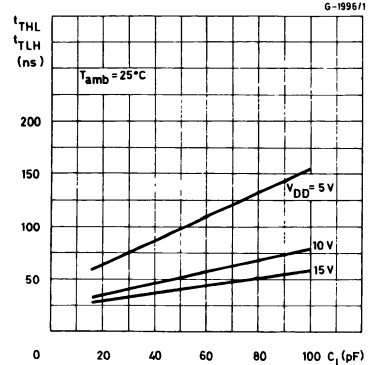
Typical Output High (source) Current Characteristics.



Minimum Output-p-channel Drain Characteristics.

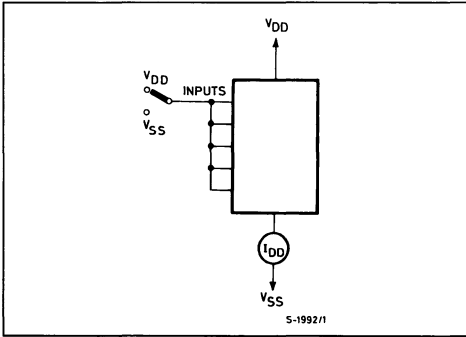


Typical Transition Time vs. C_L.

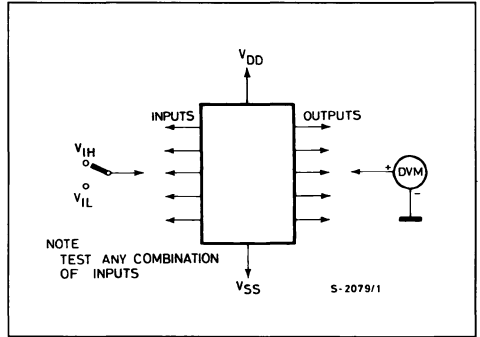


TEST CIRCUITS

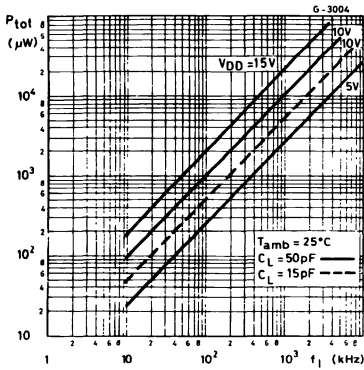
Quiescent Device Current.



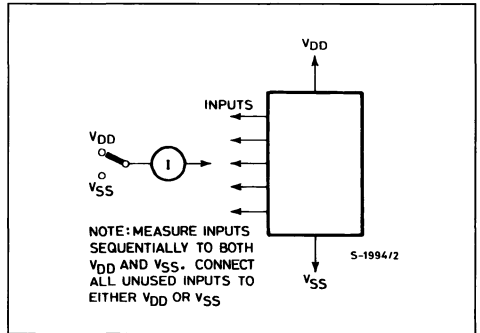
Input Voltage.



Typical Dynamic Power Dissipation vs. Frequency.



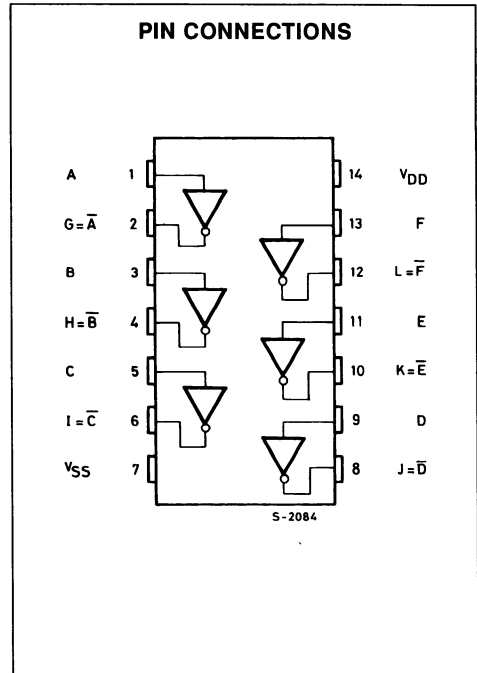
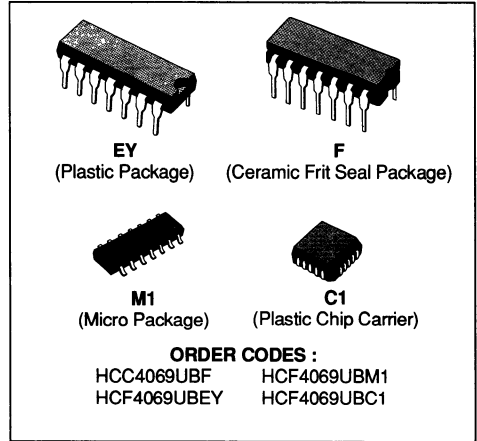
Input Current.





HEX INVERTER

- MEDIUM-SPEED OPERATION
 - $t_{PHL}, t_{PLH} = 30ns$ (typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

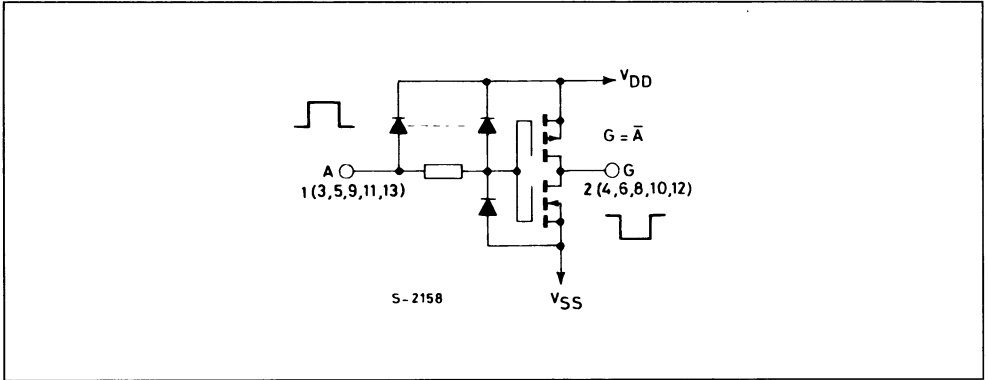


DESCRIPTION

The **HCC4069UB** (extended temperature range) and **HCF4069UB** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4069UB** consists of six COS/MOS inverter circuits. This device is intended for all general-purpose inverter applications where the medium-power TTL-drive and logic-level-conversion capabilities of circuits such as **HCC/HCF4049B** Hex Inverter/Buffers are not required.

SCHEMATIC DIAGRAM OF ONE OF SIX IDENTICAL INVERTERS.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

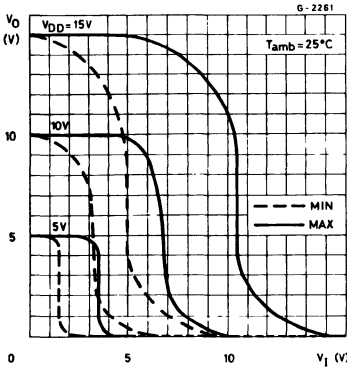
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V	
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	4		4			4		V	
			1/9	< 1	10	8		8			8			
			1.5/13.5	< 1	15	12.5		12.5			12.5			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1			1		1	V	
			9/1	< 1	10		2			2		2		
			13.5/1.5	< 1	15		2.5			2.5		2.5		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1		
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = -55°C for HCC device : -40°C for HCF device* T_{High} = +125°C for HCC device : +85°C for HCF deviceThe Noise Margin for both "1" and "0" level is .1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

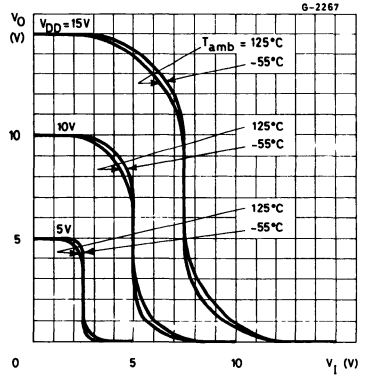
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		55	110	ns
			10		30	60	
			15		25	50	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

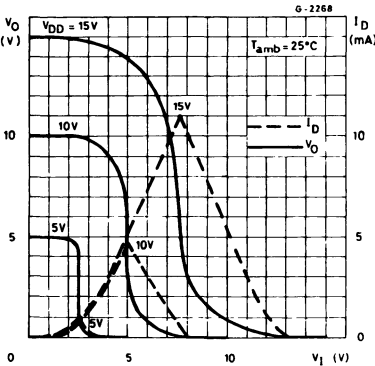
Minimum and Maximum Voltage Transfer Characteristics.



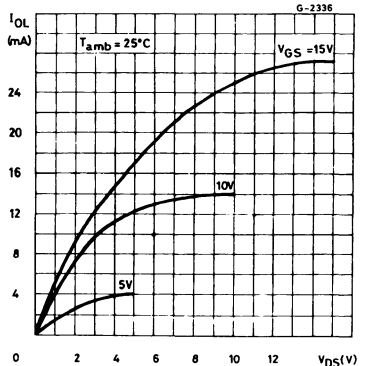
Typical Voltage Transfer Characteristics as a Function of Temperature.



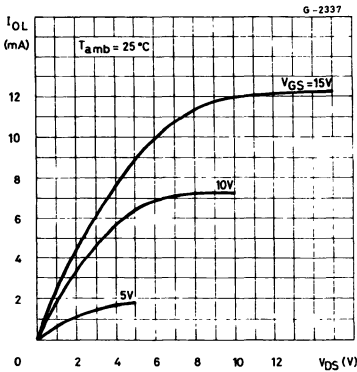
Typical Current and Voltage Transfer Characteristics.



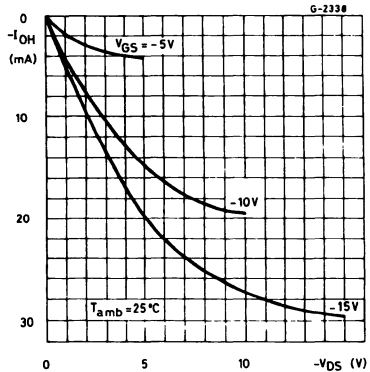
Typical Output Low (sink) Current Characteristics.



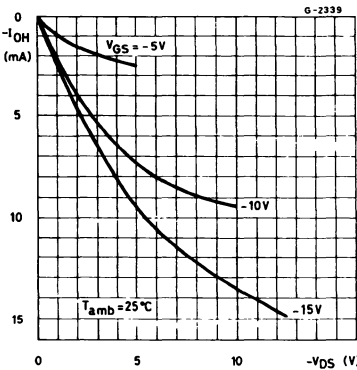
Minimum Output Low (sink) Current Characteristics.



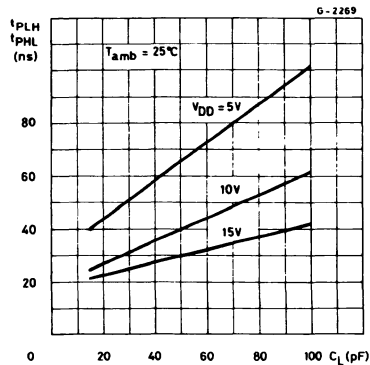
Typical Output High (source) Current Characteristics.



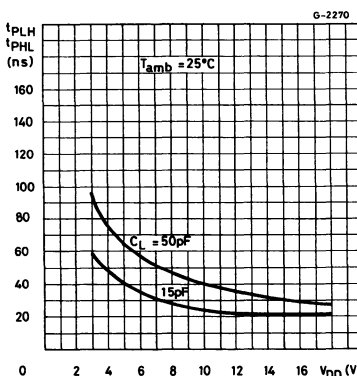
Minimum Output High (source) Current Characteristics.



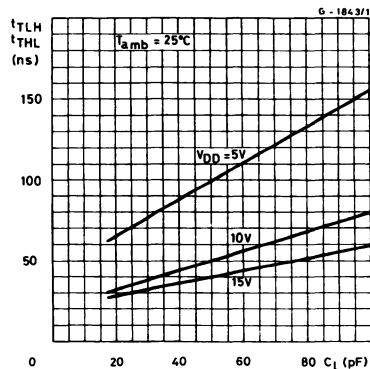
Typical Propagation Delay Time vs. Load Capacitance.



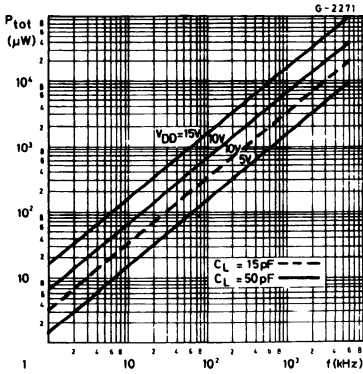
Typical Propagation Delay Time vs. Load Capacitance.



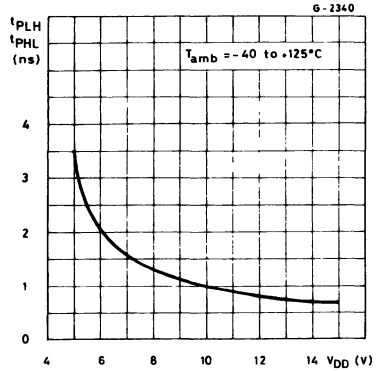
Typical Transition Time vs. Load Capacitance.



Typical Dynamic Power Dissipation/per Inverter vs. Frequency.

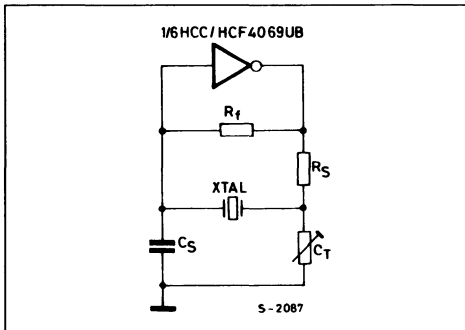


Variation of Normalized Propagation Delay Time (t_{PLH} and t_{PLH}) with Supply Voltage.

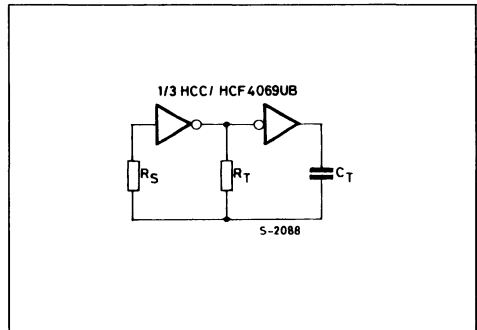


APPLICATIONS

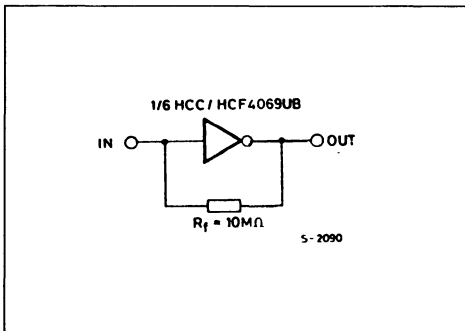
Typical Crystal Oscillator Circuit.



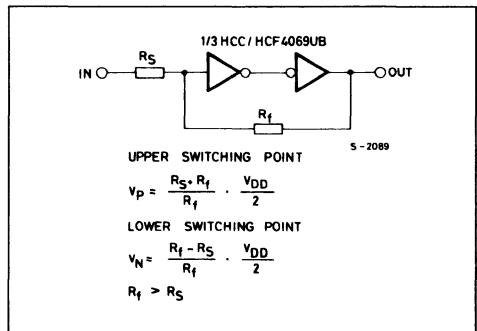
Typical RC Oscillator Circuit.



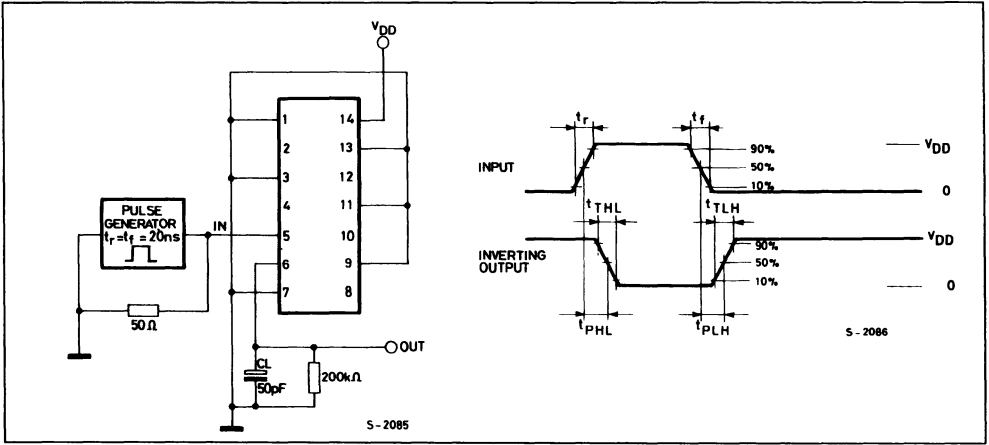
High Input Impedance Amplifier.



Input Pulse Shaping Circuit (schmitt trigger).

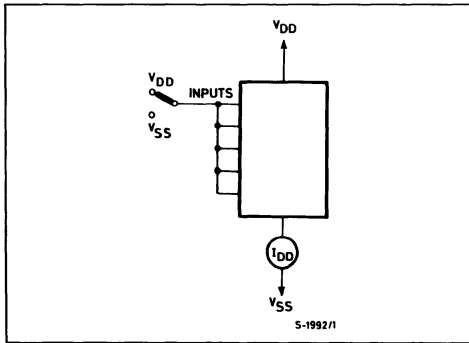


DYNAMIC ELECTRICAL CHARACTERISTICS AND WAVEFORMS

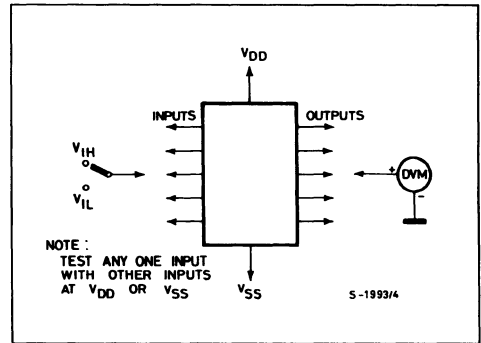


TEST CIRCUITS

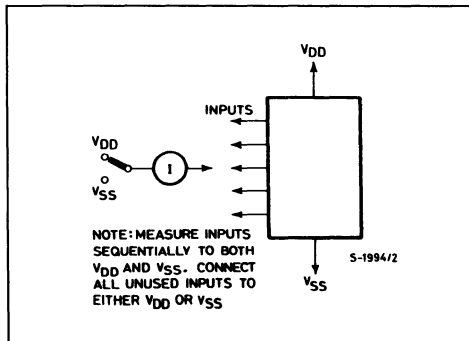
Quiescent Device Current.



Noise Immunity.

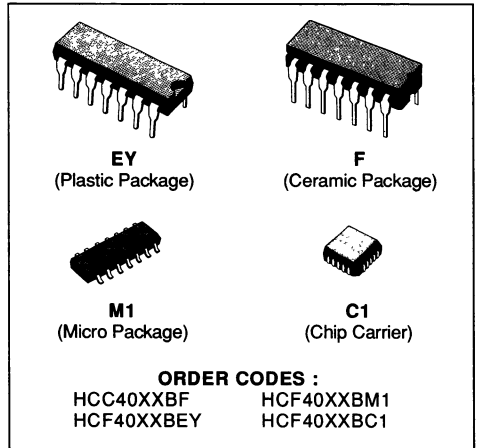


Input Leakage Current.



GATES
4070B—QUAD EXCLUSIVE-OR GATE
4037B—QUAD EXCLUSIVE-NOR GATE

- MEDIUM-SPEED OPERATION $t_{PHL} = t_{PLH} = 70\text{ns}$ (typ.) AT $V_{CC} = 10\text{V}$, $C_L = 50\text{pF}$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

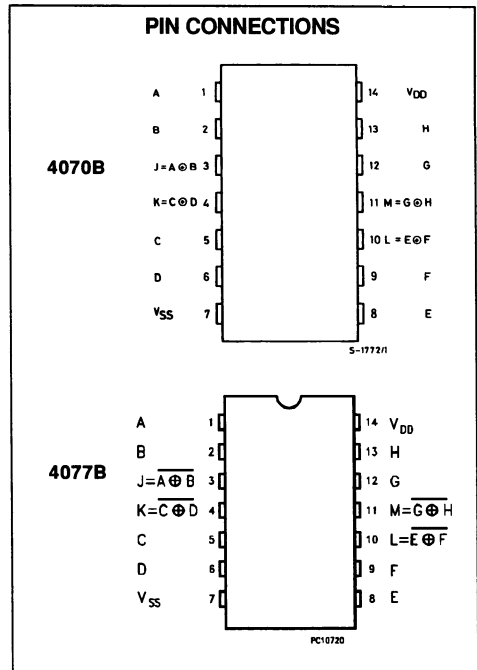

DESCRIPTION

The **HCC4070B/4077B** (extended temperature range) and **HCF4070B/4077B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

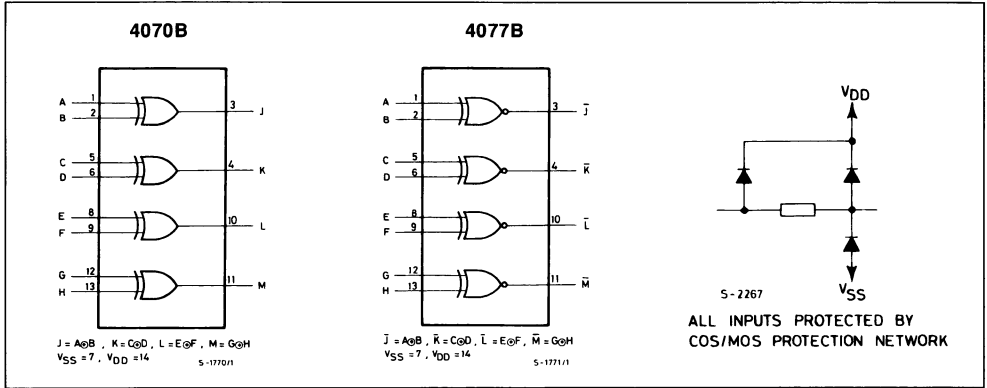
The **HCC/HCF4070B** contains four independent exclusive-OR gates.

The **HCC/HCF4077B** contains four independent exclusive-NOR gates.

The **HCC/HCF4070B** and **HCC/HCF4077B** provide the system designer with a means for direct implementation of the exclusive-OR and exclusive-NOR function, respectively. For applications as Logical comparators, Adders/subtractors, Parity generators and checkers.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200 100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C

TRUTH TABLES (1 of 4 gates)

HCC4070B		
A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

HCC4077B		
A	B	J
0	0	1
1	0	0
0	1	0
1	1	1

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

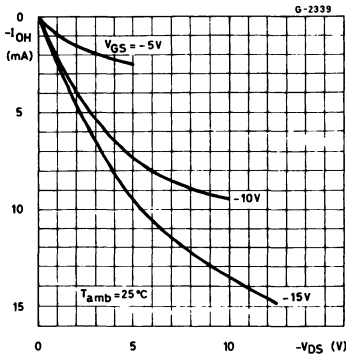
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
		0/20			20		20		0.04	20		600		
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
0/15				15		16		0.02	16		120			
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OL}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
		0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
0/10	9.5			10	-1.3		-1.1	-2.6		-0.9				
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

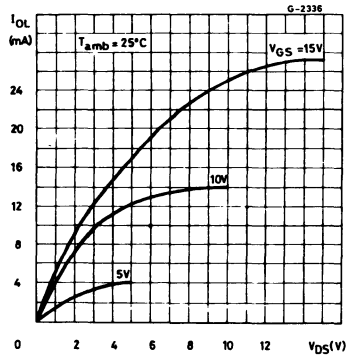
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	5			140	280	ns
		10			65	130	
		15			50	100	
t_{TLH} t_{THL}	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

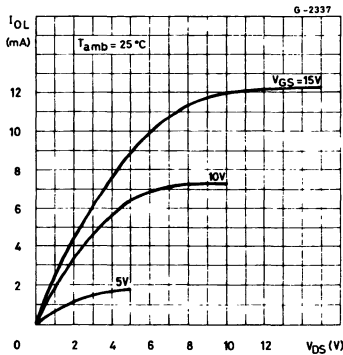
Minimum Output High (source) Current Characteristics.



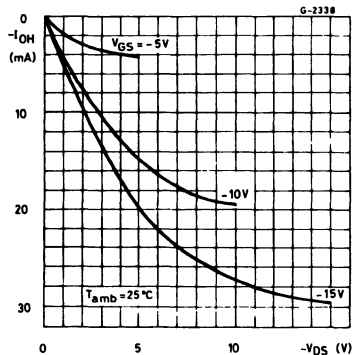
Typical Output Low (sink) Current.



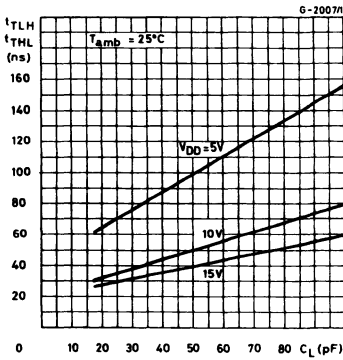
Minimum Output Low (sink) Current Characteristics.



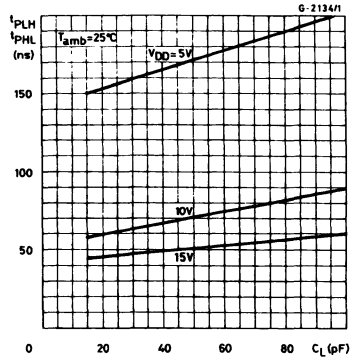
Typical Output High (source) Current Characteristics.



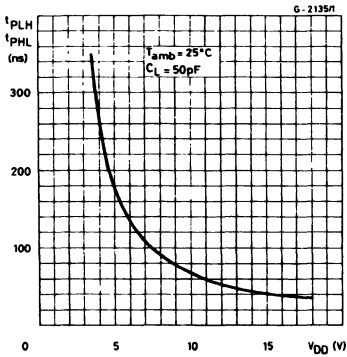
Typical Transition Time vs. Load Capacitance.



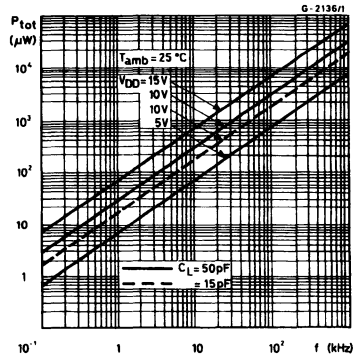
Typical Propagation Delay Time vs. Load Capacitance.



Typical Propagation Delay Time vs. Supply Voltage.

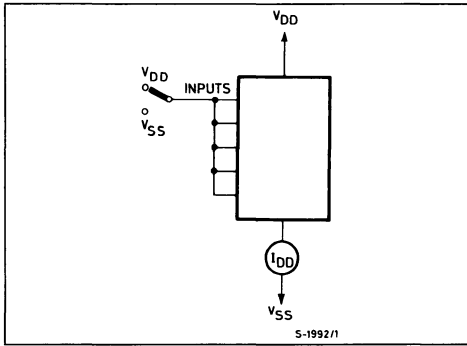


Typical Dynamic Power Dissipation vs. Input Frequency.

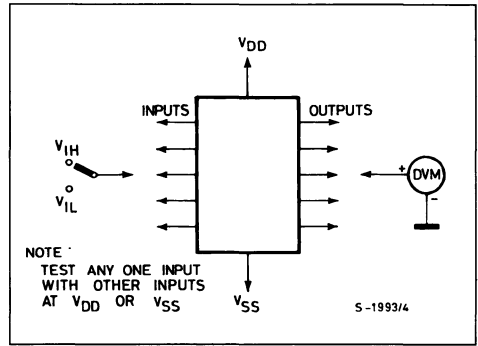


TEST CIRCUIT

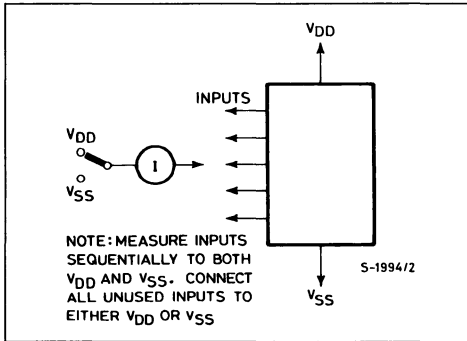
Quiescent Device Current.



Input Voltage.



Input Leakage Current.



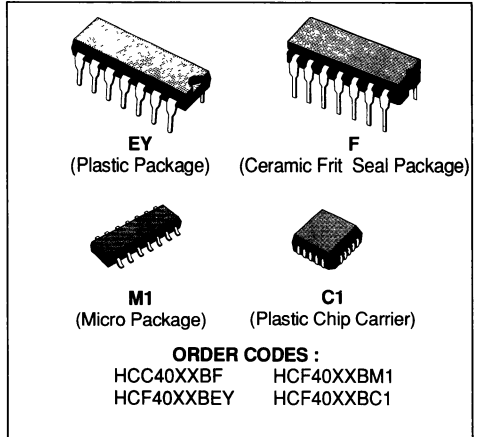
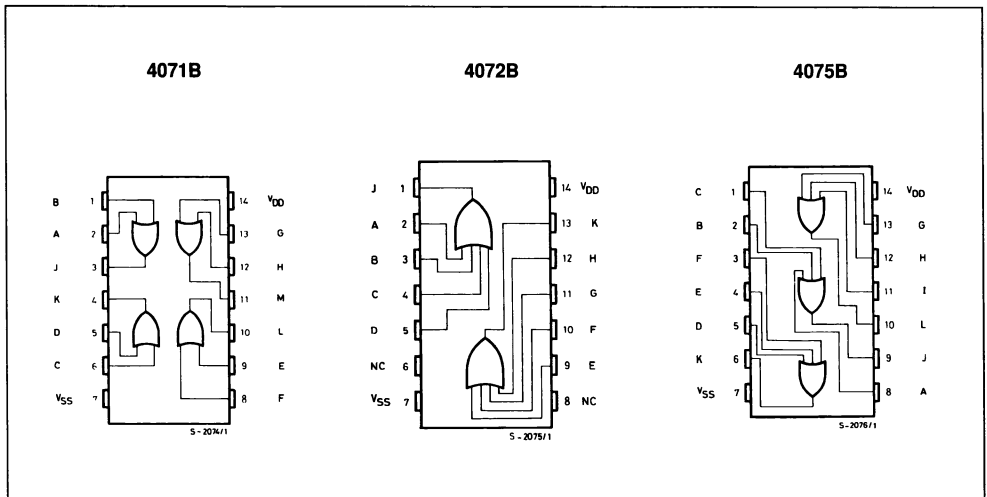
OR GATE

4071B - QUAD 2-INPUT OR GATE
4072B - QUAD 4-INPUT OR GATE
4075B - TRIPLE 3-INPUT OR GATE

- MEDIUM-SPEED OPERATION t_{PLH} , t_{PHL} = 60ns. (typ.) AT $V_{DD} = 10V$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4071B/4072B** and **4075B** (extended temperature range) and **HCF4071B/4072B** and **4075B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

PIN CONNECTIONS


The **HCC/HCF4071B, 4072B** and **4075B** OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of COS/MOS gates.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

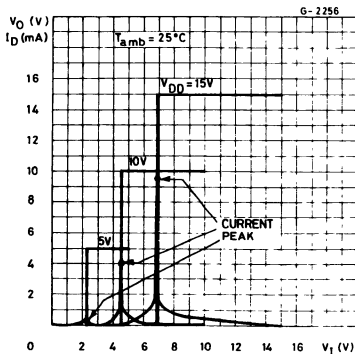
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

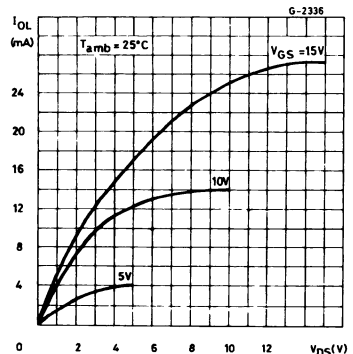
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

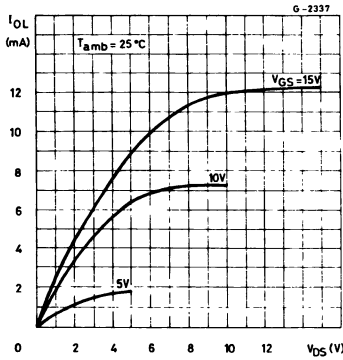
Typical Voltage and Current Transfer Characteristics.



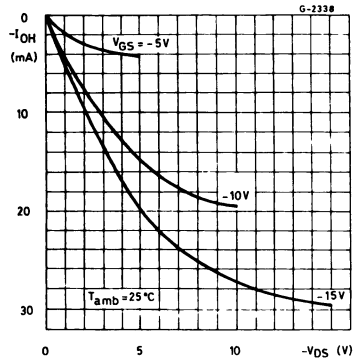
Typical Output Low (sink) Current Characteristics.



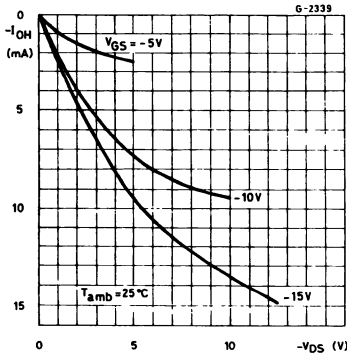
Minimum Output Low (sink) Current Characteristics.



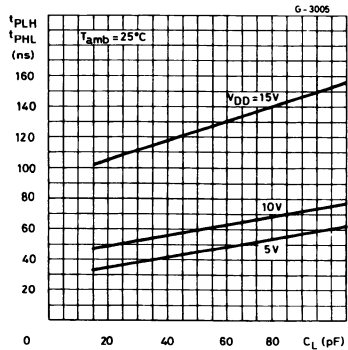
Typical Output High (source) Current Characteristics.



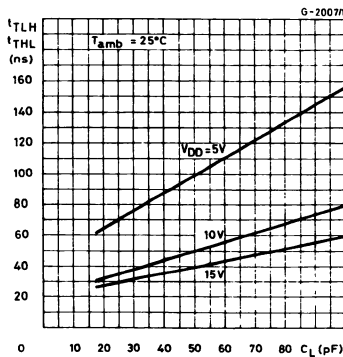
Minimum Output High (source) Current Characteristics.



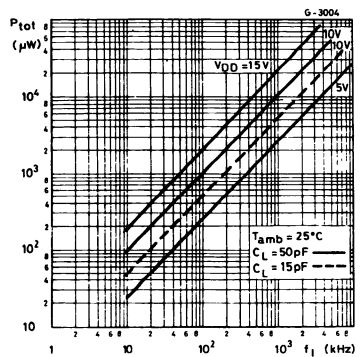
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

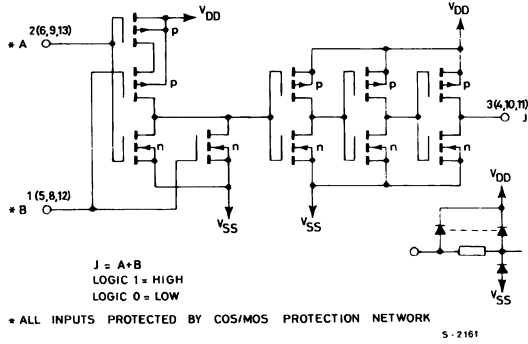


Typical Dynamic Power Dissipation vs. Frequency.

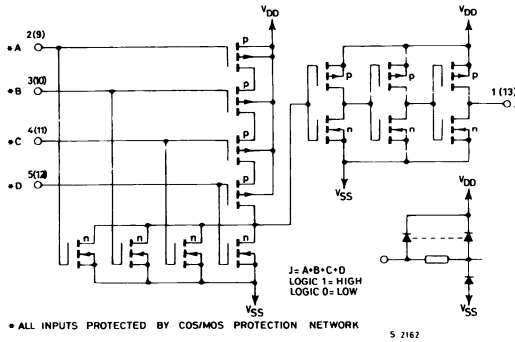


SCHEMATIC DIAGRAMS

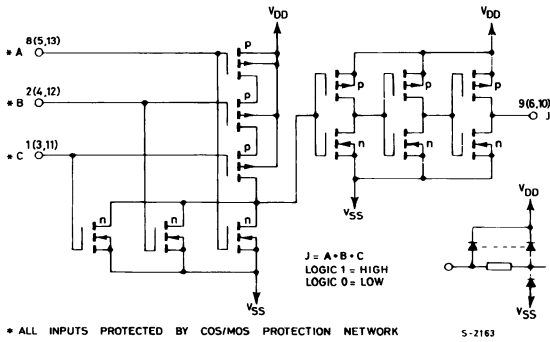
4071B – 1 of 4 identical OR gates



4072B – 1 of 2 identical OR gates



4075B – 1 of 3 identical OR gates



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V		
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5		1.5		1.5	V		
			9/1	< 1	10		3		3		3			
			13.5/1.5	< 1	15		4		4		4			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1		
C _I	Input Capacitance		Any Input						5	7.5		pF		

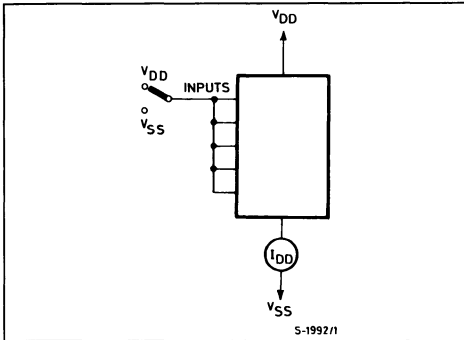
* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device* T_{High} = + 125°C for HCC device ; + 85°C for HCF deviceThe Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

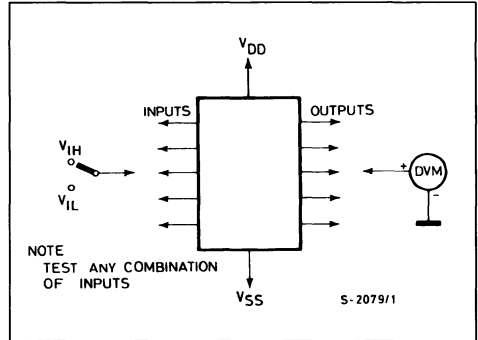
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			15		45	90	
t_{PLH}	Propagation Delay Time		5		175	350	ns
			70		50	140	
			15		50	140	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

TEST CIRCUITS

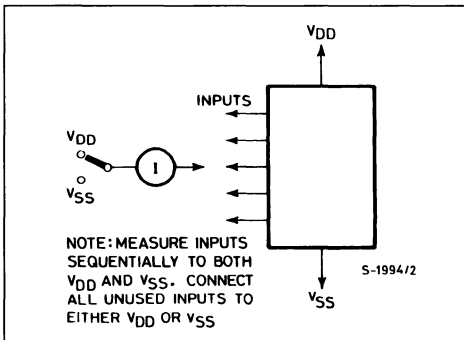
Quiescent Device Current.



Input Voltage.



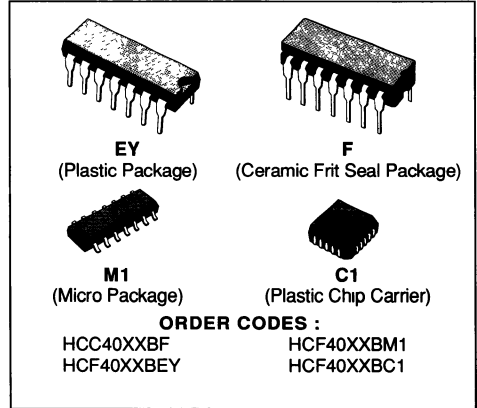
Input Leakage Current.



AND GATES

- 4073B TRIPLE 3-INPUT AND GATE**
4081B QUAD 2-INPUT AND GATE
4082B DUAL 4-INPUT AND GATE

- MEDIUM SPEED OPERATION – $t_{PLH} = 85\text{ns}$ (typ.) ; $t_{PHL} = 65\text{ns}$ (typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



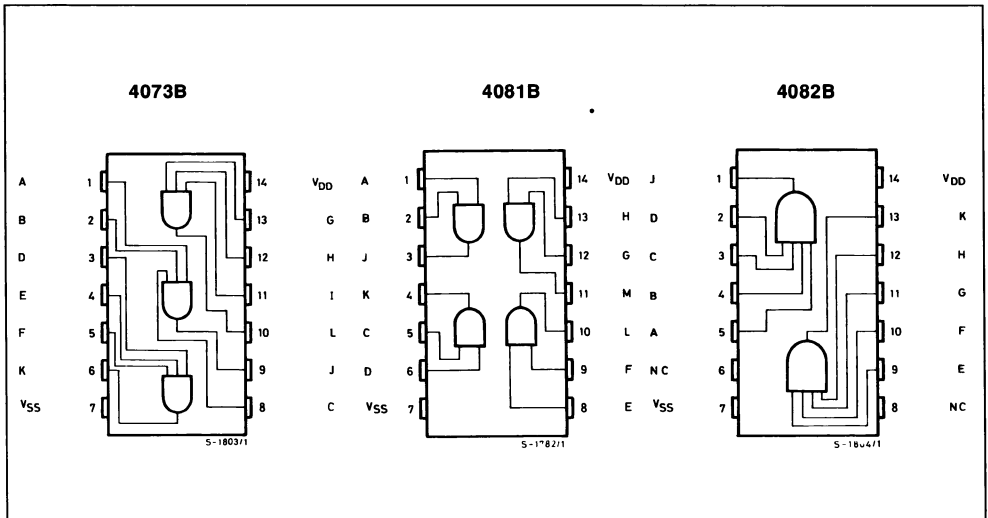
DESCRIPTION

The **HCC4073B**, **HCC4081B** and **HCC4082B** (extended temperature range) and the **HCF4073B**, **HCF4081B** and **HCF4082B** (intermediate temperature range) are monolithic integrated circuits available in 14-lead dual in-line plastic or ceramic pack-

age and plastic micro package.

The **HCC/HCF4073B**, **4081B** and **4082B** AND gates provide the system designer with direct implementation of the AND function and supplement the existing family of COS/MOS gates.

CONNECTION DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (µA)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		0.25		0.01	0.25		7.5	µA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V	
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			

* T_{Low} = - 55°C for HCC device - 40°C for HCF device

* T_{High} = + 125°C for HCC device + 85°C for HCF device

The Noise Margin for both "1" and "0" level is . 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V
			9/1	< 1	10		3			3		3	
			13.5/1.5	< 1	15		4			4		4	
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36	
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9	
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4	
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1	
			0/5	4.6		5	-0.52		-0.44	-1		-0.36	
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9	
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5		pF	

* T_{Low} = -55°C for HCC device : -40°C for HCF device.

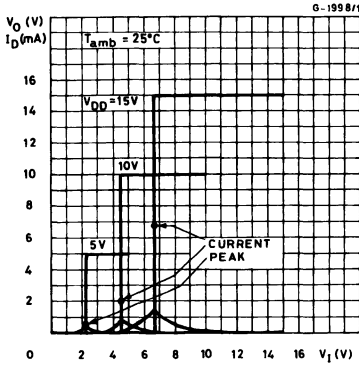
* T_{High} = +125°C for HCC device : +85°C for HCF device.

The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

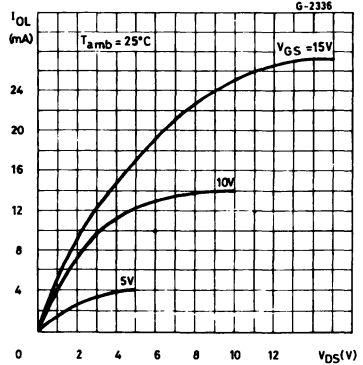
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall times = 20ns, R_L = 200k Ω)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PHL} , t _{PLH}	Propagation Delay Time		5		125	250	ns
			10		60	125	
			15		45	90	
t _{TLH} , t _{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

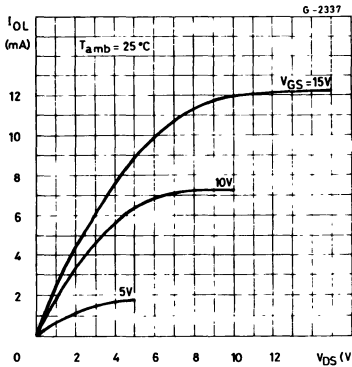
Typical Voltage and Current Transfer Characteristics.



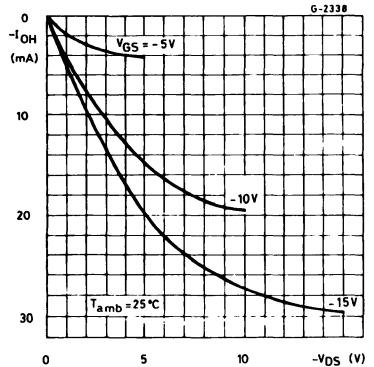
Typical Output Low (sink) Current .



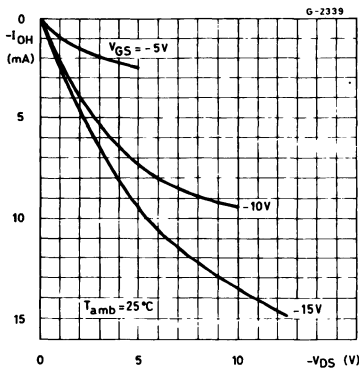
Minimum Output Low (sink) Current Characteristics.



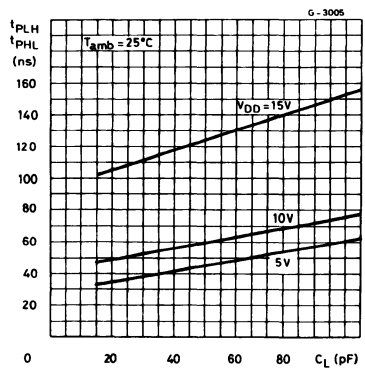
Typical Output High (source) Current Characteristics.



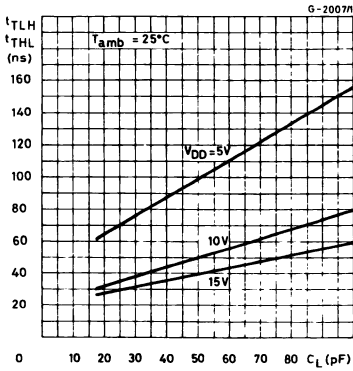
Minimum Output High (source) Current Characteristics.



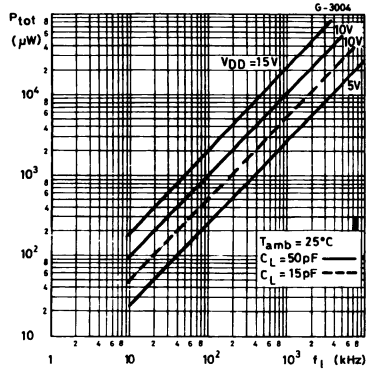
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

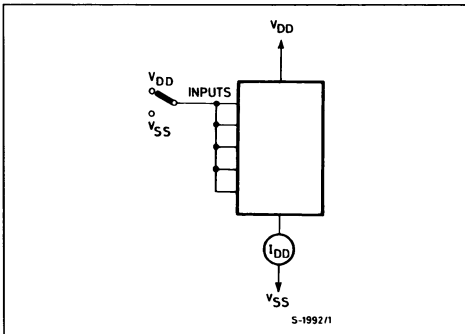


Typical Dynamic Power Dissipation per Gate vs. Frequency.

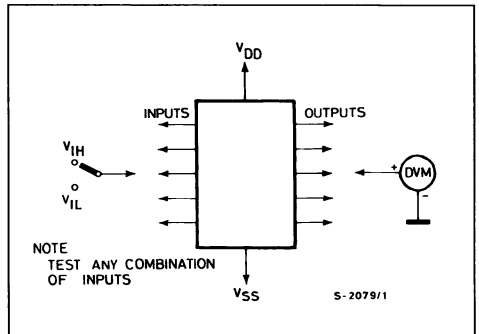


TEST CIRCUITS

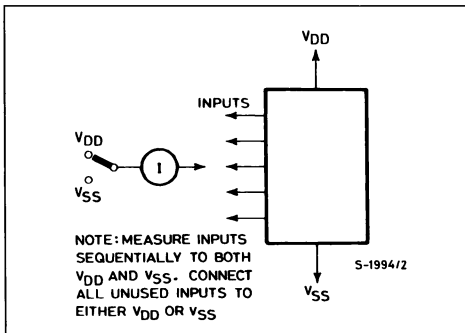
Quiescent Device Current.



Input Voltage.

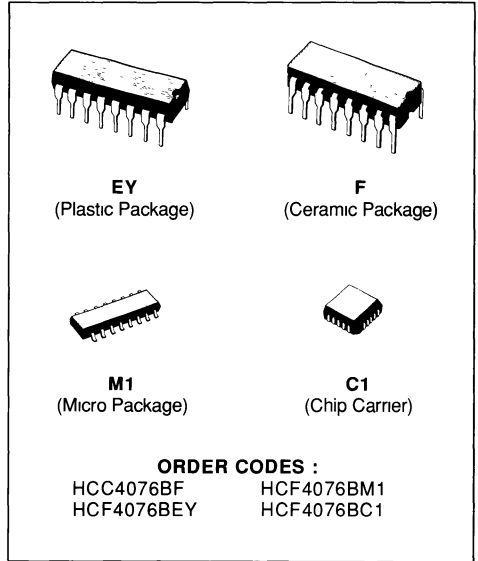


Input Leakage Current.



4 BIT D TYPE REGISTERS

- THREE STATE OUTPUTS
- INPUT DISABLE WITHOUT GATING THE CLOCK
- GATED OUTPUT CONTROL LINES FOR ENABLING OR DISABLING THE OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES "

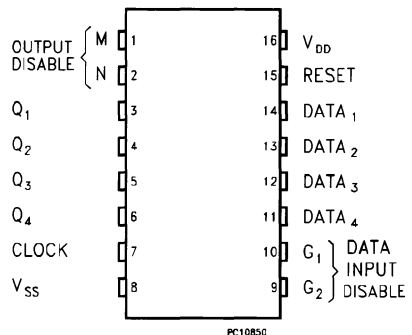


DESCRIPTION

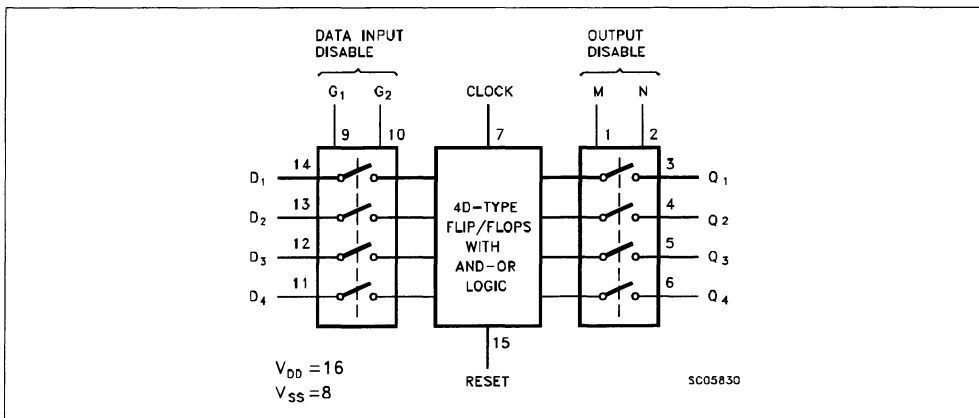
The **HCC4076B** (extended temperature range) and **HCC4076B** (intermediate temperature range) are monolithic integrated circuit, available in 16 lead dual in line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4076B** types are four-bit registers consisting of D-type flip-flops that feature three-state outputs. Data Disable inputs are provided to control the entry of data into the flip-flops. When both Data Disable inputs are low, data at the D inputs are loaded into their respective flip-flops on the next positive transition of the clock input. Output Disable inputs are also provided. When the Output Disable inputs are both low, the normal logic states of the four outputs are available to the load. The outputs are disabled independently of the clock by a high logic level at either Output Disable input, and present a high impedance.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

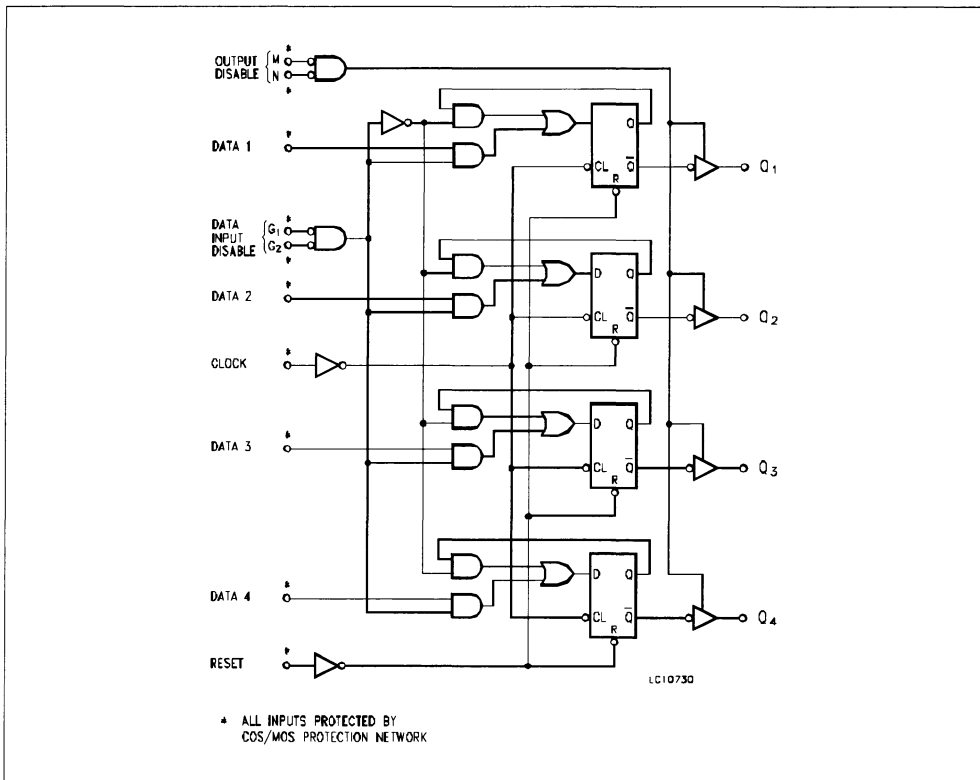
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

LOGIC DIAGRAM



TRUTH TABLE

RESET	CLOCK	DATA INPUT DISABLE		DATA D	NEXT STATE OUTPUT G	
		G1	G2			
1	X	X	X	X	0	
0	0	X	X	X	Q	NC
0		1	X	X	Q	NC
0		X	1	X	Q	NC
0		0	0	1	1	
0		0	0	0	0	
0	1	X	X	X	Q	NC
0		X	X	X	Q	NC

When either Output Disable M or N is high, the outputs are disabled (high impedance state), however sequential operation of the flip-flop is not affected.
 1 = High Level, 0 = Low Level, X = Don't Care, NC = No Change

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

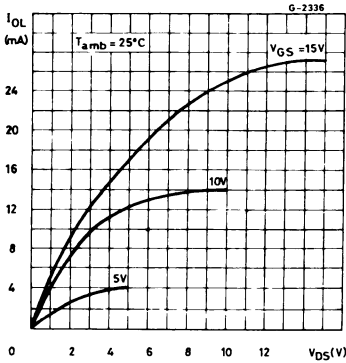
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.61		0.44	1		0.36		
			0/10	0.5		10	1		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	0/18			18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		0/15		Any Input	15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	μ A	
I _{OH} , I _{OL}	Input Leakage Current	HCC Types	0/18	0/18		18		\pm 0.4		\pm 10 ⁻⁴	\pm 0.4		\pm 12	μ A
		HCF Types	0/15	0/15		15		\pm 1.0		\pm 10 ⁻⁴	\pm 1.0		\pm 7.5	μ A
C _I	Input Capacitance								5	7.5			pF	

* T_{LOW} = -55 °C for HCC device -40 °C for HCF device* T_{HIGH} = +125 °C for HCC device +85 °C for HCF deviceThe Noise Margin for both "1" and "0" level is. 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

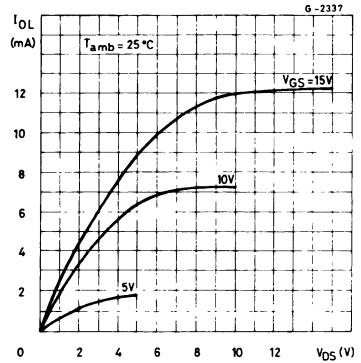
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}/\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time (Clock to Q Output)		5		300	600	ns
			10		125	250	
			15		90	180	
$t_{PHL}(R)$	Propagation Delay Time (Reset)		5		230	460	ns
			10		100	200	
			15		75	150	
$t_{P(1-H)}$ $t_{P(0-H)}$	3-State Output 1 or 0 to High Impedance	$R_L = 1\text{ K}\Omega$	5		150	300	ns
			10		75	150	
			15		60	120	
$t_{P(H-1)}$ $t_{P(L-1)}$	3-State High Impedance to 1 or 0 Output	$R_L = 1\text{ K}\Omega$	5		150	300	ns
			10		75	150	
			15		60	120	
t_w	Clock Pulse Width		5	200	100		ns
			10	100	50		
			15	80	40		
t_w	Reset Pulse Width		5	120	60		ns
			10	50	25		
			15	40	20		
t_{setup}	Data Setup Time		5	200	100		ns
			10	80	40		
			15	60	30		
t_{setup}	Data Input Disable Setup Time		5	180	90		ns
			10	100	50		
			15	70	35		
f_{max}	Maximum Clock Frequency		5	3	6		MHz
			10	6	12		
			15	8	16		
t_r, t_f	Clock Input Rise or Fall Time		5	15			μs
			10	5			
			15	5			

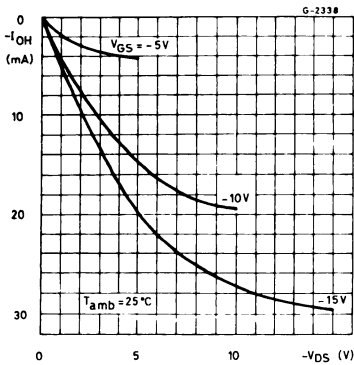
Typical Output Low (sink) Current Characteristics



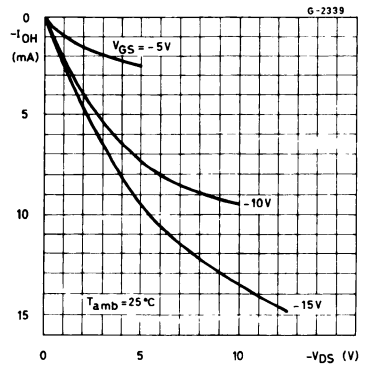
Minimum Output Low (sink) Current Characteristics



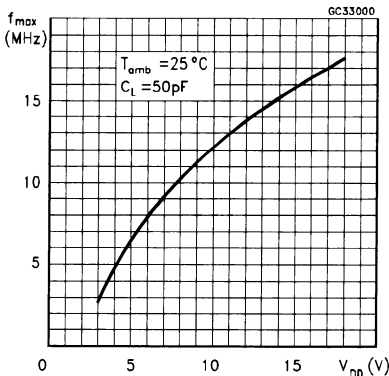
Typical Output High (source) Current Characteristics



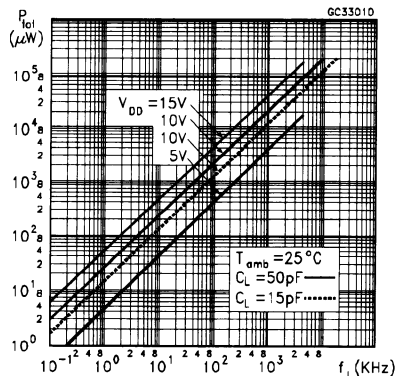
Minimum Output High (source) Current Characteristics



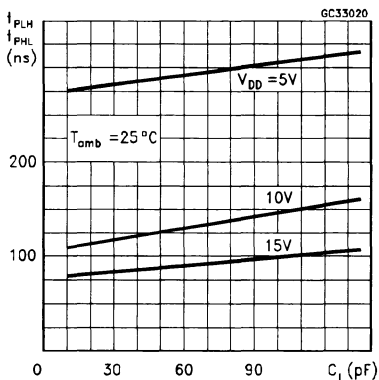
Typical Maximum Clock Input Frequency vs Supply Voltage



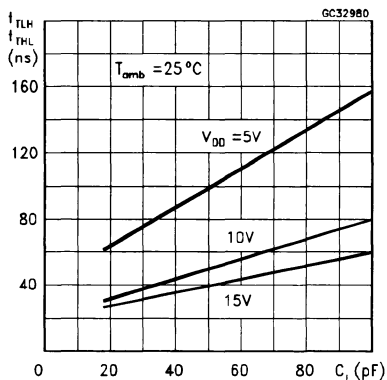
Typical Dynamic Power Dissipation vs Frequency



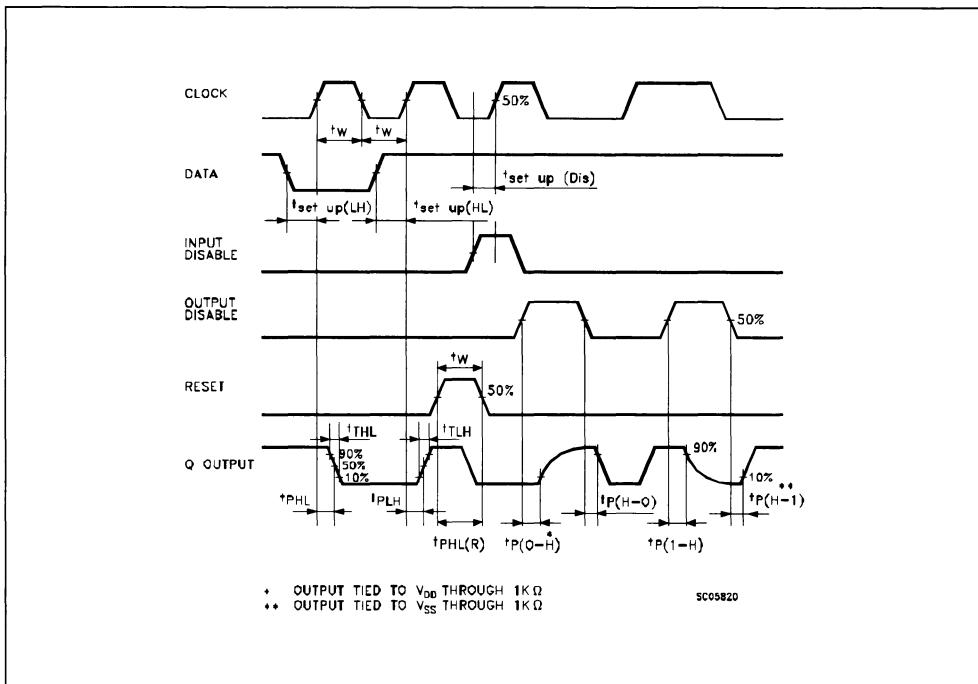
Typical Propagation Delay Time vs Capacitance



Typical Transition Time vs Load Capacitance

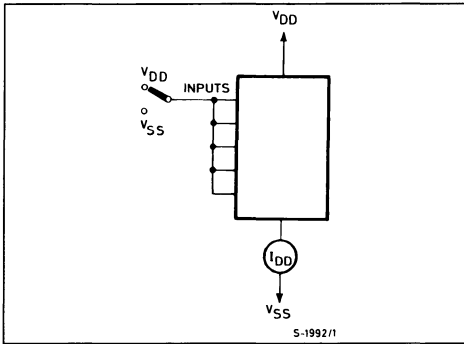


WAVEFORMS

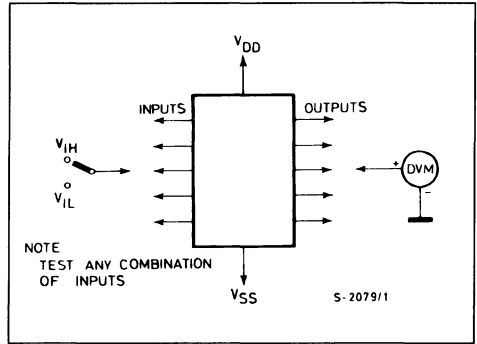


TEST CIRCUITS

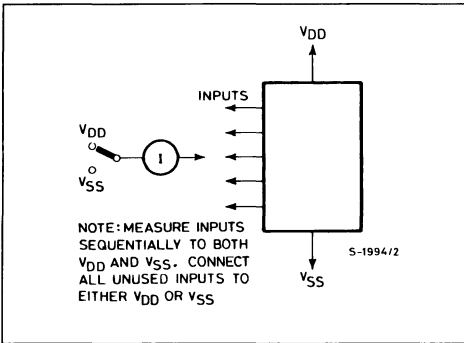
Quiescent Device Current.



Noise Immunity.

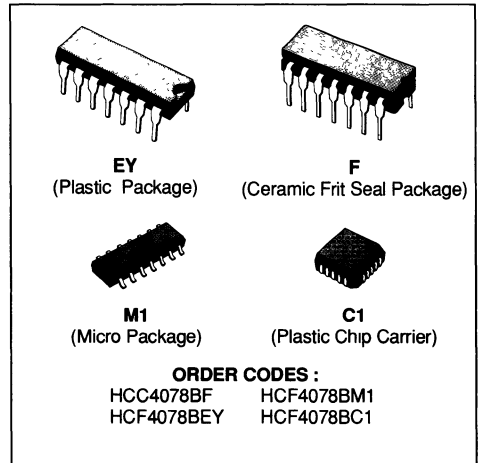


Input Leakage Current.



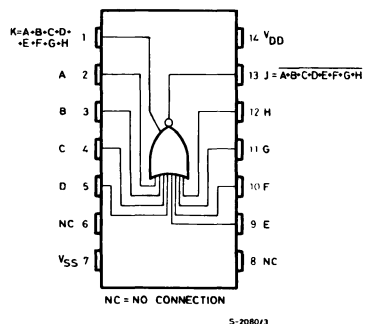
8-INPUT NOR/OR GATE

- MEDIUM-SPEED OPERATION t_{PHL} , $t_{PLH} = 75\text{ns}$ (TYP.) AT $V_{DD} = 10\text{V}$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

The **HCC4078B** (extended temperature range) and **HCF4078B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package, plastic micropackage.

The **HCC/HCF4078B** NOR/OR Gate provides the system designer with direct implementation of the positive-logic-8-input NOR and OR function and supplements the existing family of COS/MOS gates.

PIN CONNECTIONS


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{Tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{Op} = Full Package-temperature Range	200	mW
		100	mW
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T_{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		0.25		0.01	0.25		7.5	μ A
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15											
C _I	Input Capacitance		Any Input						5	7.5			pF	

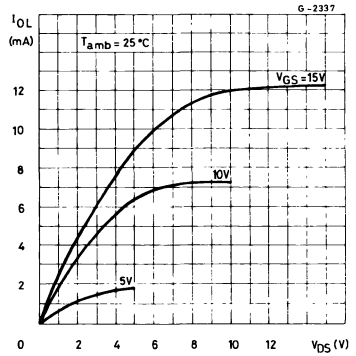
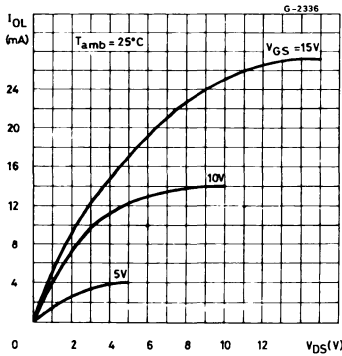
* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time	5		150	300	ns	
		10		75	150		
		15		55	110		
t_{THL} , t_{TLH}	Transition Time	5		100	200	ns	
		10		50	100		
		15		40	80		

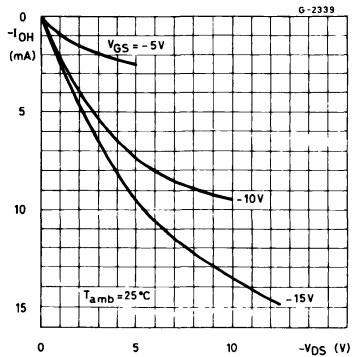
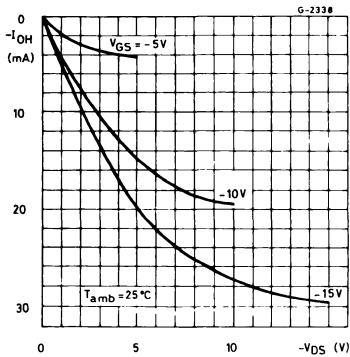
Typical Output Low (sink) Current Characteristics.

Minimum Output Low (sink) Current Characteristics.

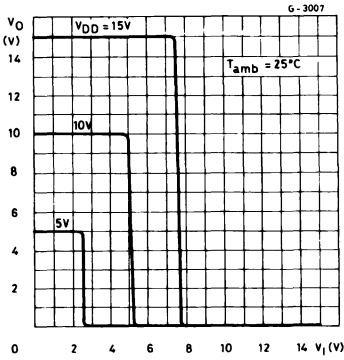


Typical Output High (source) Current Characteristics.

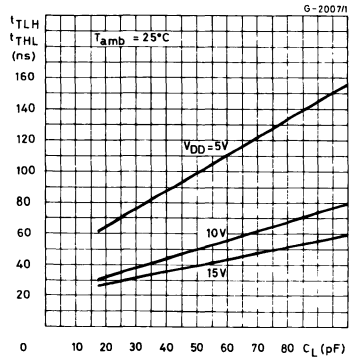
Minimum Output High (source) Current Characteristics.



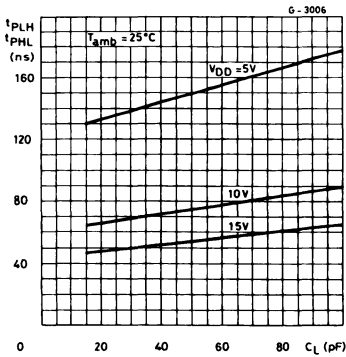
Typical Voltage Transfer Characteristics (NOR output).



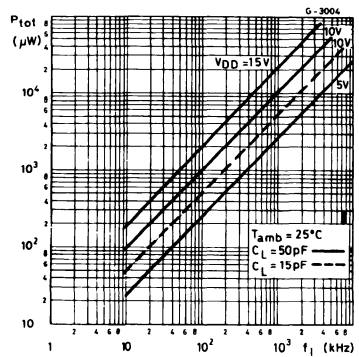
Typical Transition Time vs. Load Capacitance.



Typical Propagation Delay Time vs. Load Capacitance.

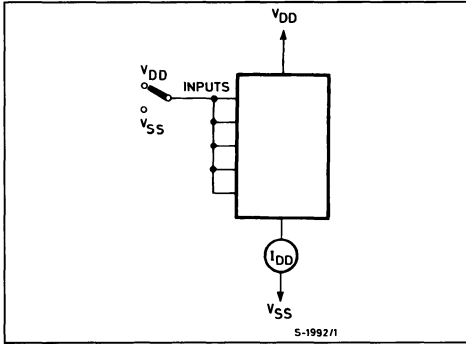


Typical Power Dissipation vs. Frequency.

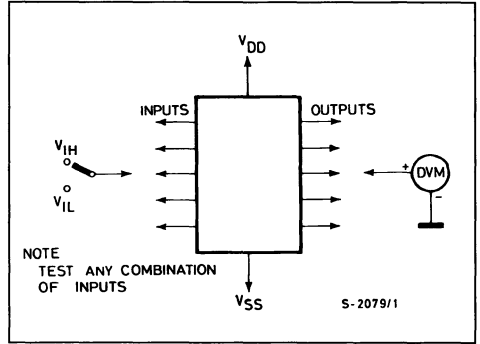


TEST CIRCUITS

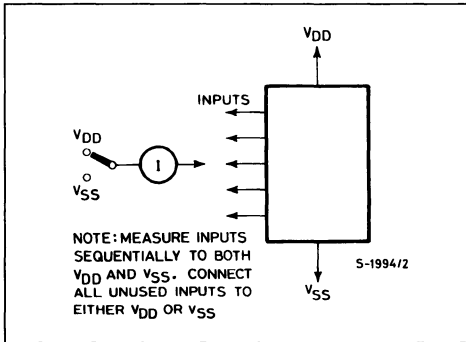
Quiescent Device Current.



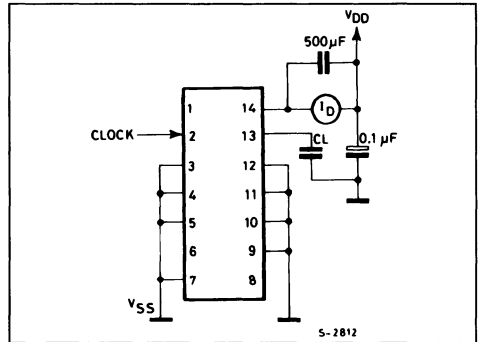
Input Voltage.



Input Current.

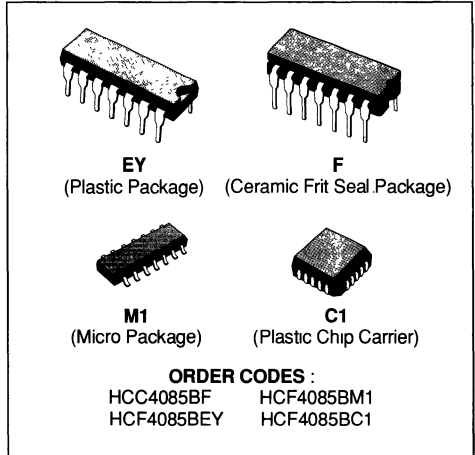


Dynamic Power Dissipation.



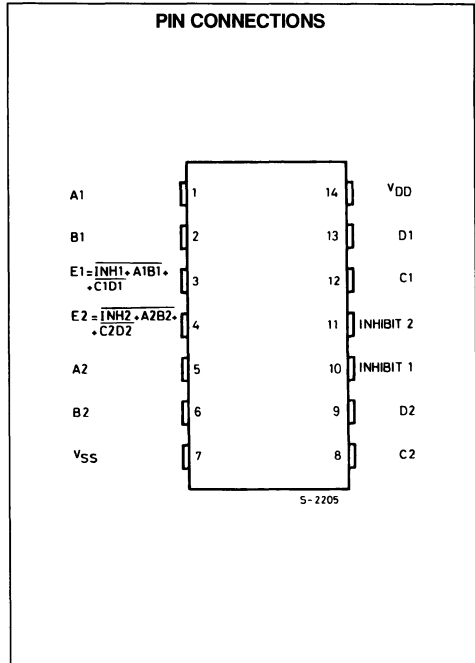
DUAL 2-WIDE 2-INPUT AND-OR-INVERTER GATE

- MEDIUM-SPEED OPERATION – $t_{PHL} = 90\text{ns}$; $t_{PLH} = 125\text{ns}$ (TYP.) AT 10V
- INDIVIDUAL INHIBIT CONTROLS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

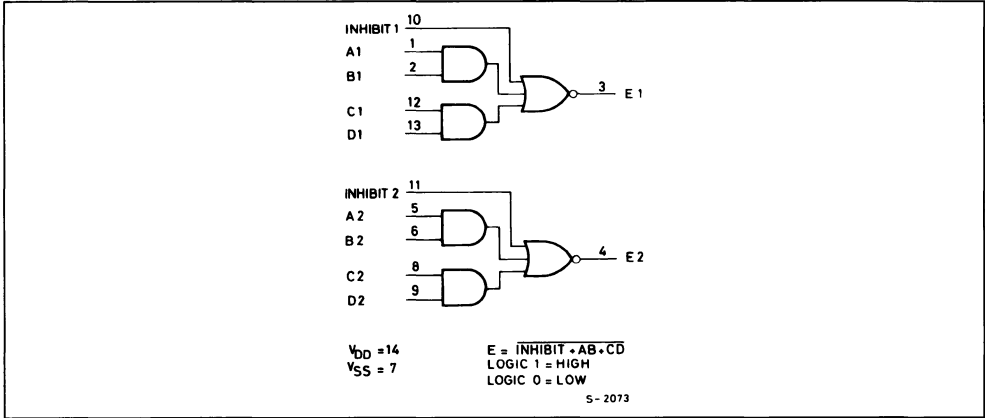

DESCRIPTION

The **HCC4085B** (extended temperature range) and **HCF4085B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4085B** contains a pair of AND-OR-INVERT gates, each consisting of two 2-input AND gates driving a 3-input NOR gate. Individual inhibit controls are provided for both A-O-I gates.



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

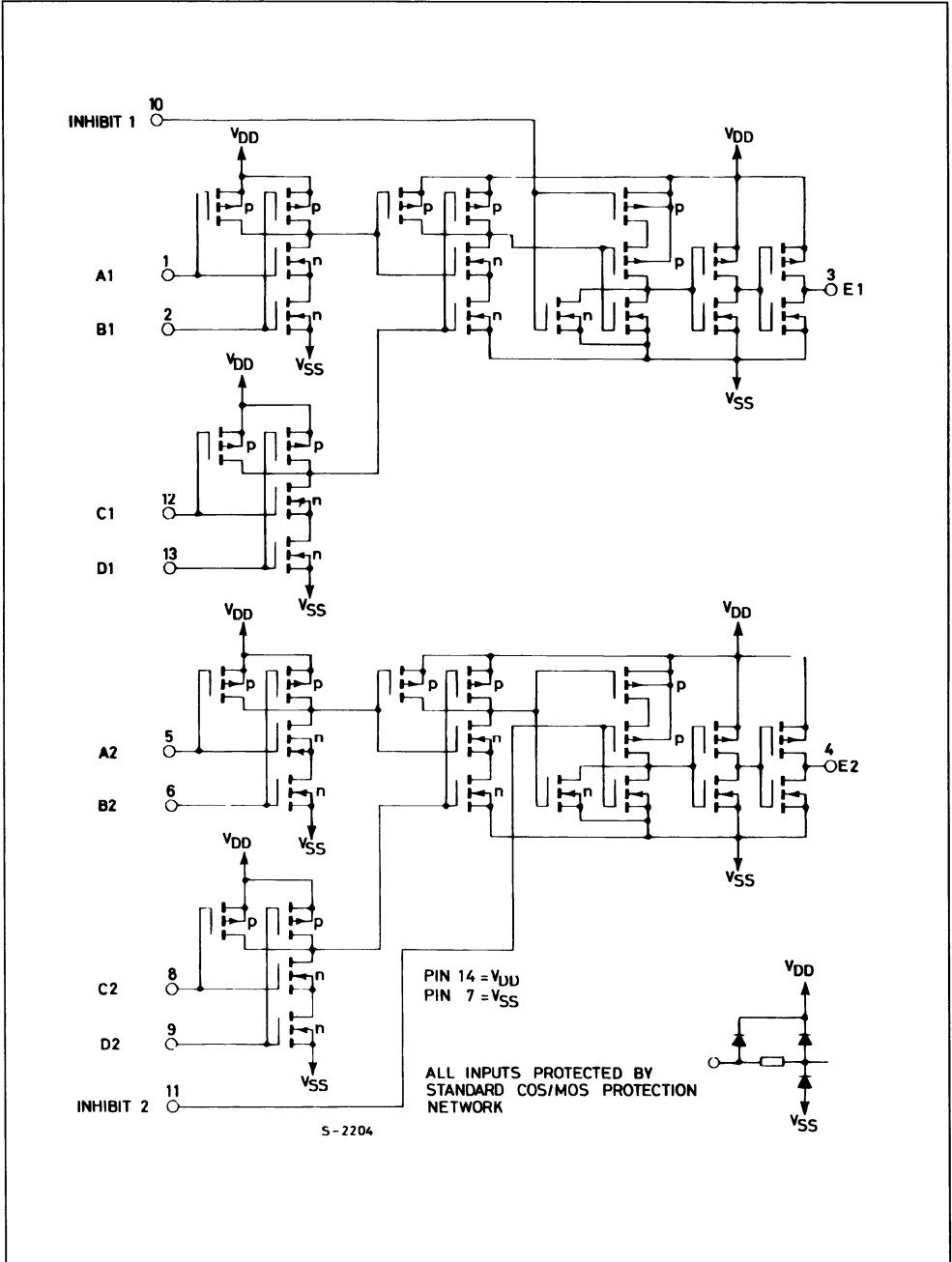
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability
 * All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$

SCHEMATIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

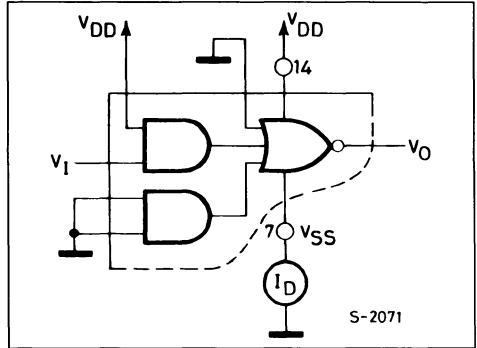
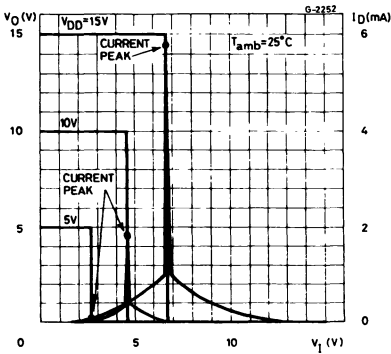
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V	
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15			15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1		
C _I	Input Capacitance		Any Input						5	7.5		pF		

* T_{Low} = -55°C for HCC device - 40°C for HCF device.* T_{High} = +125°C for HCC device + 85°C for HCF device.The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5min with V_{DD} = 15V

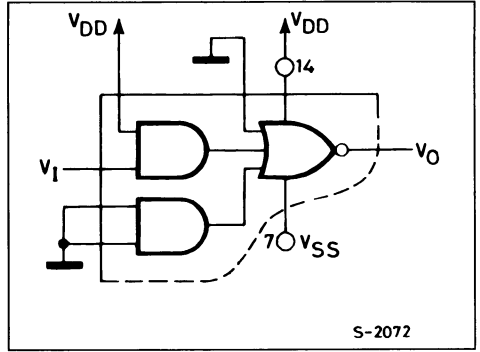
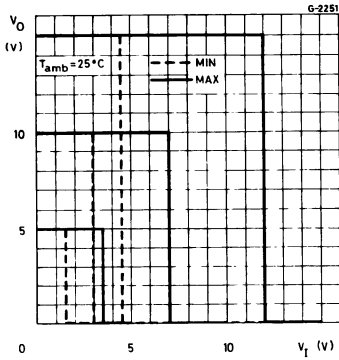
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time (data)		5		225	450	ns
			10		90	180	
			15		65	130	
t_{PLH}	Propagation Delay Time (data)		5		310	620	ns
			10		125	250	
			15		90	180	
t_{PHL}	Propagation Delay Time (inhibit)		5		150	300	ns
			10		60	120	
			15		40	80	
t_{PLH}	Propagation Delay Time (inhibit)		5		250	500	ns
			10		100	200	
			15		70	140	
t_{TLH}, t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

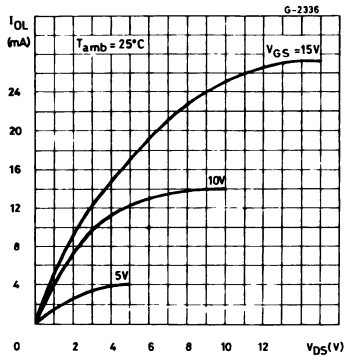
Typical Voltage and Current Transfer Characteristics with Test Circuit.



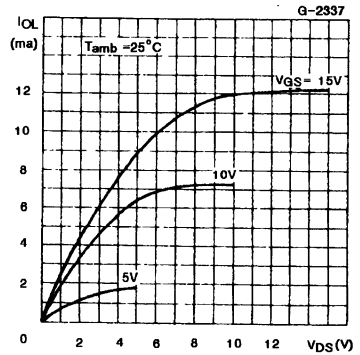
Minimum and Maximum Voltage Transfer Characteristics with Test Circuit.



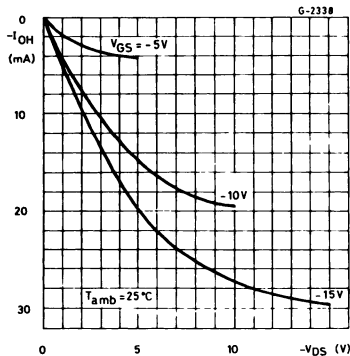
Typical Output Low (sink) Current Characteristics.



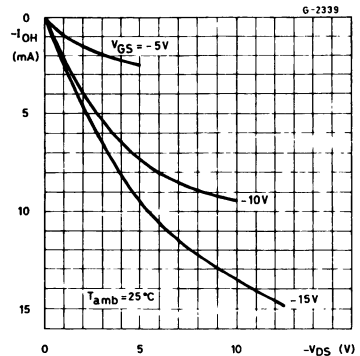
Minimum Output Low (sink) Current Characteristics.



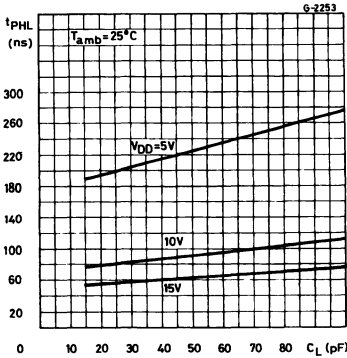
Typical Output High (source) Current Characteristics.



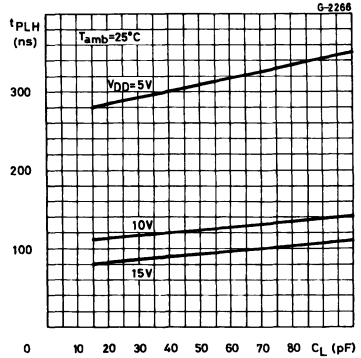
Minimum Output High (source) Current Characteristics.



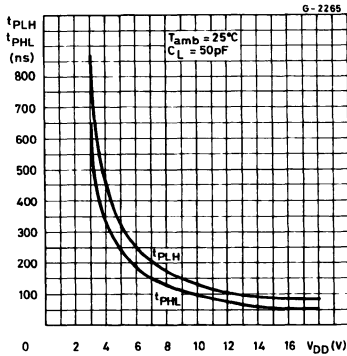
Typical Data High-to-low Level Propagation Delay Time vs. Load Capacitance.



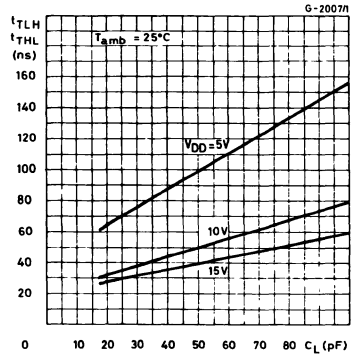
Typical Data Low-to-high Level Propagation Delay Time vs. Load Capacitance.



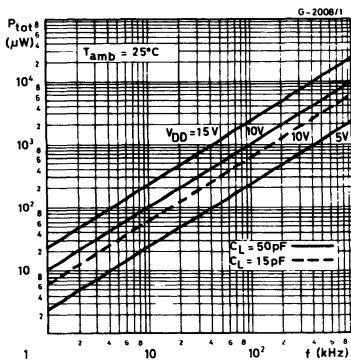
Typical Data Propagation Delay Time vs. Supply Voltage.



Typical Transition Time vs. Load Capacitance.

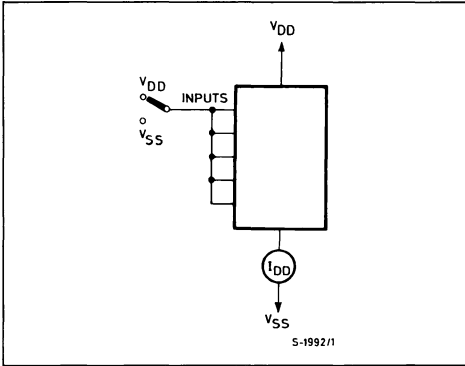


Typical Power Dissipation vs. Frequency.

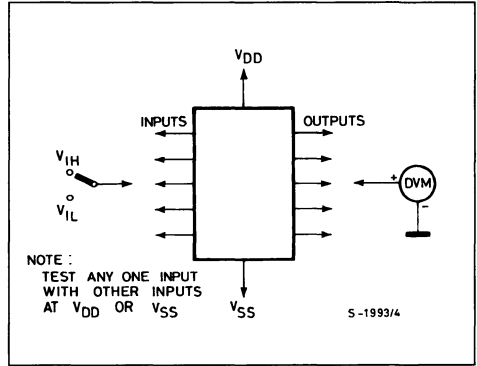


TEST CIRCUITS

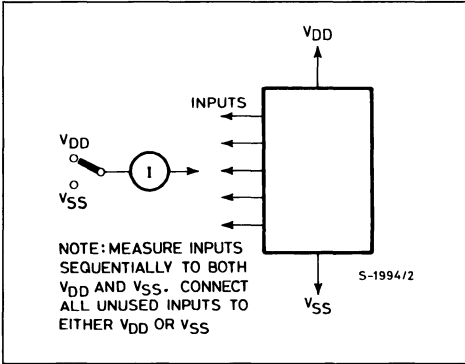
Quiescent Device Current.



Input Voltage.

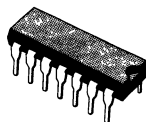
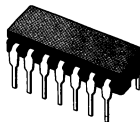


Input Current.



**EXPANDABLE 4 WIDE 2 INPUT
 AND OR INVERT GATE**

- MEDIUM SPEED OPERATION: $t_{PHL} = 90ns$;
 $t_{PLH} = 140ns$ (TYP.) AT 10V
- INHIBIT AND ENABLE INPUTS
- BUFFERED OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V
 FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT
 CHACACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25oC
 FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TEN-
 TATIVE STANDARD N. 13A, "STANDARD
 SPECIFICATIONS FOR DESCRIPTION OF 'B'
 'SERIES CMOS DEVICES "


EY
 (Plastic Package)

F
 (Ceramic Package)

M1
 (Micro Package)

C1
 (Chip Carrier)

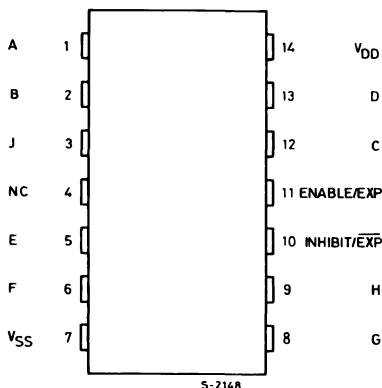
ORDER CODES :

HCC4086BF	HCF4086BM1
HCF4086BEY	HCF4086BC1

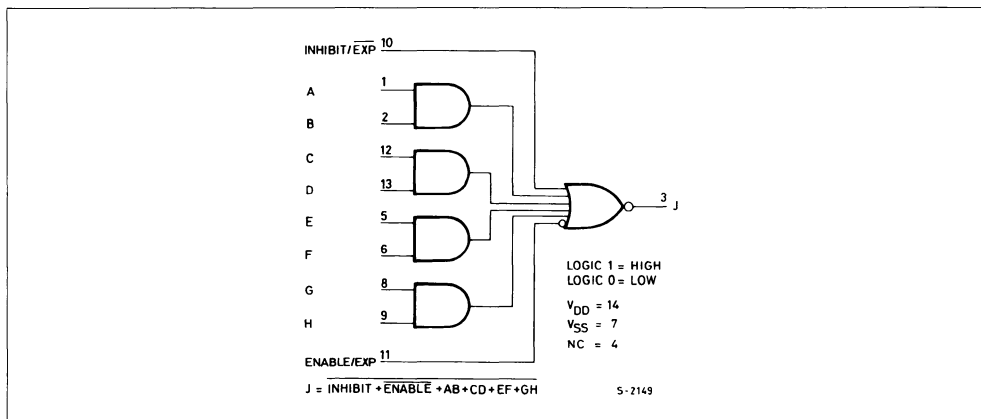
DESCRIPTION

The **HCC4086B** (extended temperature range) and **HCF4086B** (intermediate temperature range) are monolithic integrated circuit, available in 14 lead dual in line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4086B** contains one 4 wide 2 input AND OR INVERT gate with an INHIBIT/EXP input and an ENABLE/EXP input. For a 4 wide A-O-I function INHIBIT/EXP is tied to VSS and ENABLE/EXP to VDD. See application and its associated explanation for applications where a capability greater than 4 wide is required.

PIN CONNECTIONS


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage: HCC Types HCF Types	-0.5 to +20	V
		-0.5 to +18	V
V_I	Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package Temperature Range	200	mW
		100	mW
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	$^{\circ}\text{C}$
		-40 to +85	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

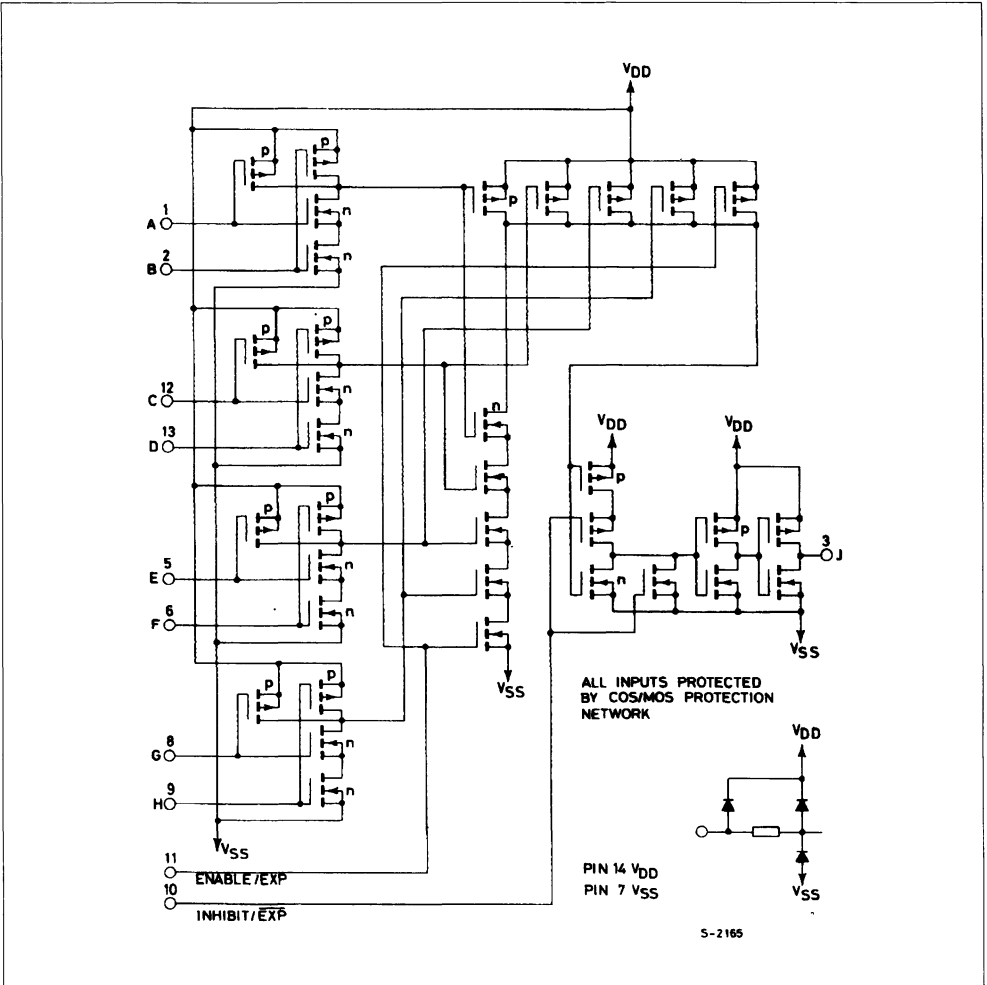
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage: HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	$^{\circ}\text{C}$
		-40 to +85	$^{\circ}\text{C}$

SCHEMATIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
V _{OH}	Output High Voltage		0/5	< 1	5	4.95		4.95			4.95		V	
			0/10	< 1	10	9.95		9.95			9.95			
			0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage		5/0	< 1	5		0.05			0.05		0.05	V	
			10/0	< 1	10		0.05			0.05		0.05		
			15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5	5	-2		-1.6	-3.2		-1.15		mA	
			0/5	4.6	5	-0.64		-0.51	-1		-0.36			
			0/10	9.5	10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5	15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5	5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6	5	-0.52		-0.44	-1		-0.36			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4	5	0.64		0.51	1		0.36		mA	
			0/10	0.5	10	1.6		1.3	2.6		0.9			
			0/15	1.5	15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4	5	0.52		0.44	1		0.36			
			0/10	0.5	10	1.3		1.1	2.6		0.9			
			0/15	1.5	15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current		0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
			0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	μ A	
C _I	Input Capacitance		Any Input					5	7.5			pF		

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device

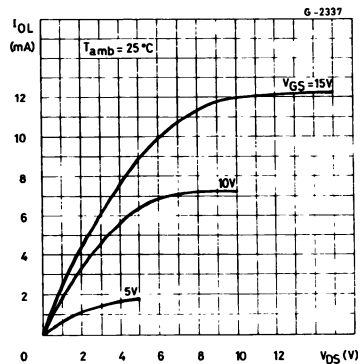
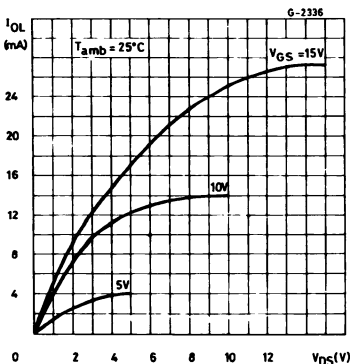
The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

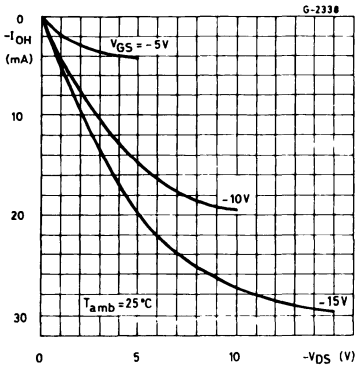
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time (Data)		5		225	450	ns
			10		90	180	
			15		60	120	
t_{PLH}	Propagation Delay Time (Data)		5		310	620	ns
			10		125	250	
			15		90	180	
t_{PHL}	Propagation Delay Time (Inhibit)		5		150	300	ns
			10		60	120	
			15		40	80	
t_{PLH}	Propagation Delay Time (Inhibit)		5		250	500	ns
			10		100	200	
			15		70	140	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

Typical Output Low (sink) Current Characteristics

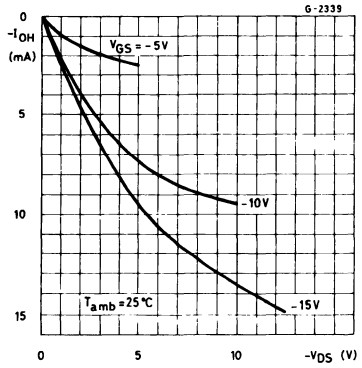
Minimum Output Low (sink) Current Characteristics



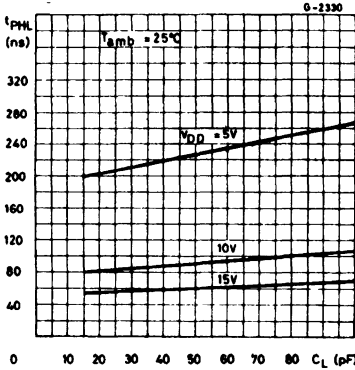
Typical Output High (source) Current Characteristics



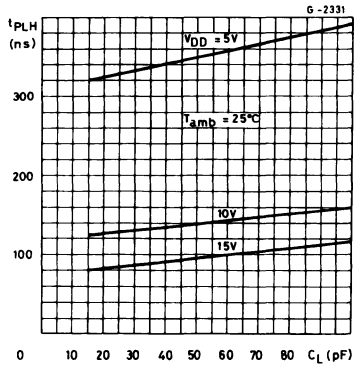
Minimum Output High (source) Current Characteristics



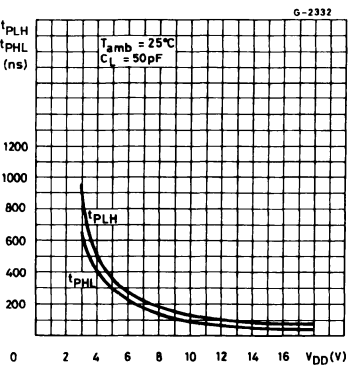
Typical DATA Or ENABLE High to Low Level Propagation Delay Time vs Load Capacitance



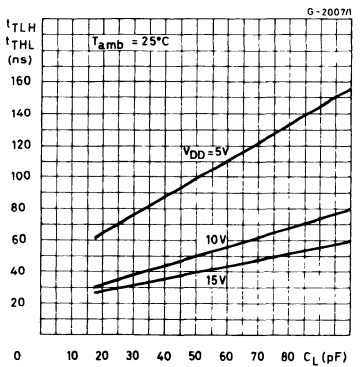
Typical DATA Or ENABLE Low to High Level Propagation Delay Time vs Load Capacitance



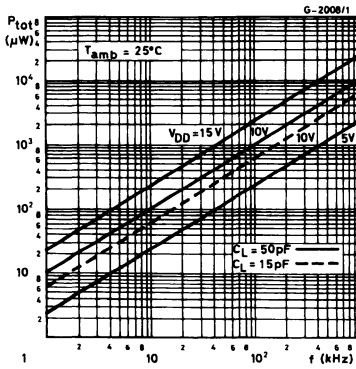
Typical DATA Or ENABLE Propagation Delay Time vs Supply Voltage



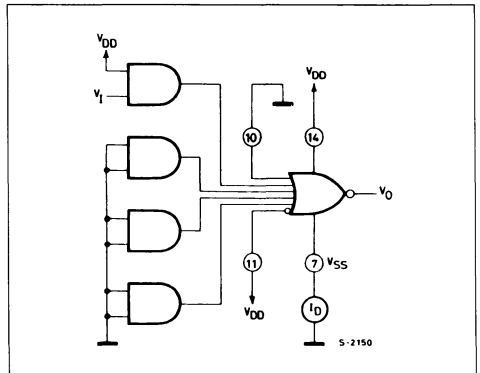
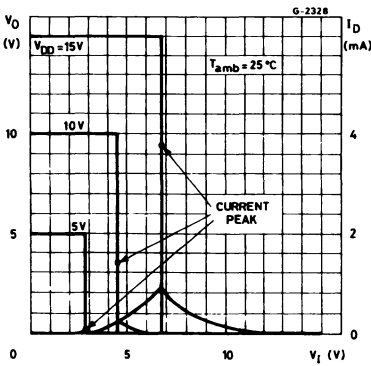
Typical Transition Time vs Load Capacitance



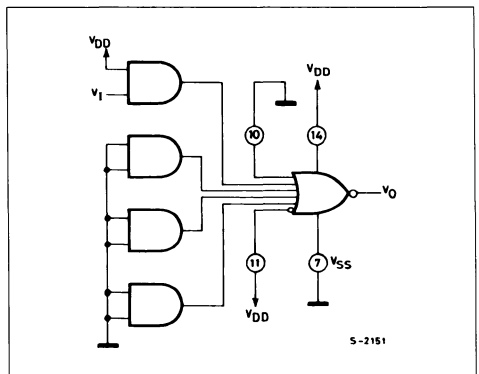
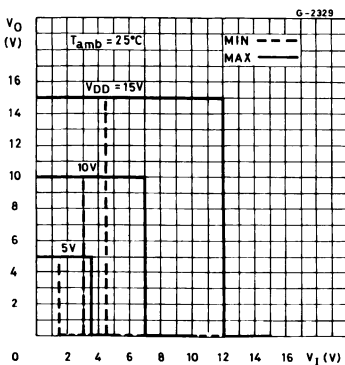
Typical Power Dissipation vs Frequency



Typical Voltage and Current Transfer Characteristics and Test Circuit

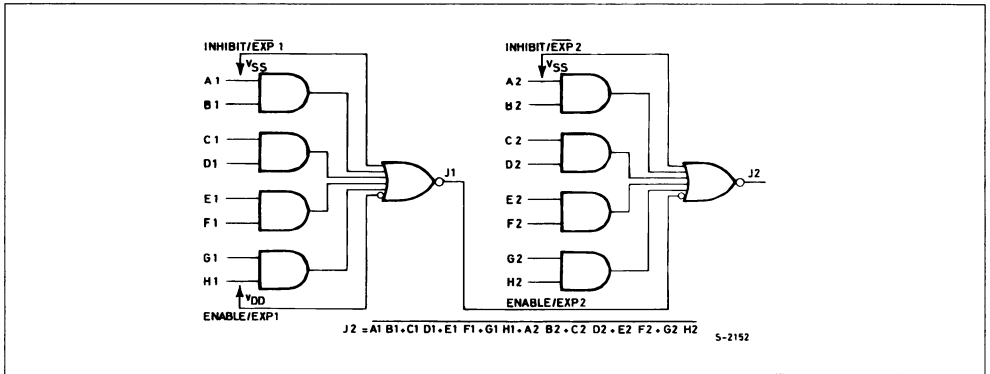


Minimum and Maximum Voltage Transfer Characteristics and Test Circuit



APPLICATION

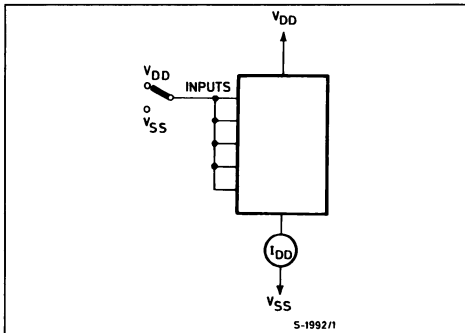
Two 4086B Connected as an 8 Wide 2 Input A-O-I Gate



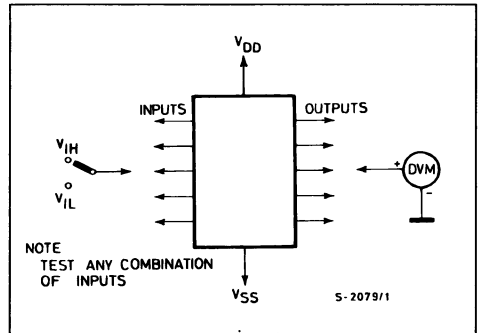
This application shows two HCC/HCF4086B utilized to obtain an 8-wide 2 input A-O-I function. The output (J1) of one HCC/HCF4086B is fed directly to the ENABLE/EXP 2 line of the second HCC/HCF4086B. In a similar fashion, any NAND gate output can be fed directly into the ENABLE/EXP input to obtain a 5 wide A-O-I function. In addition, any AND gate output can be fed directly into the INHIBIT/EXP input with the same result.

TEST CIRCUITS

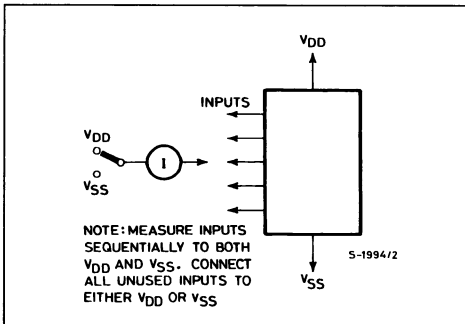
Quiescent Device Current.



Noise Immunity.

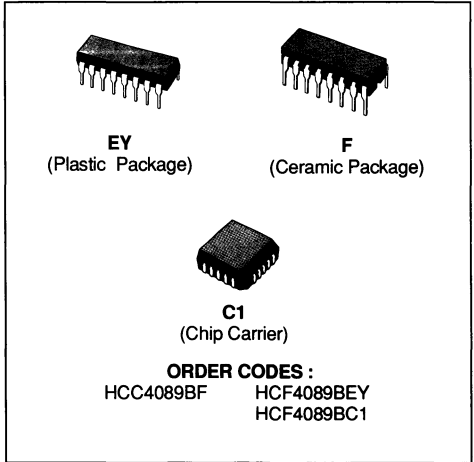


Input Leakage Current.



BINARY RATE MULTIPLIER

- CASCADABLE IN MULTIPLES OF 4-BITS
- SET TO "15" INPUT AND "15" DETECT OUTPUT
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

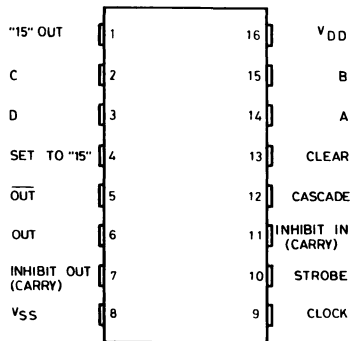
The **HCC4089B** (extended temperature range) and **HCF4089B** (intermediate temperature range) are monolithic integrated circuit available in 16-lead dual in-line plastic or ceramic package.

The **HCC/HCF4089B** is a low-power 4-bit digital rate multiplier that provides an output pulse rate that is the clock-input-pulse rate multiplied by 1/16 times the binary input. For example, when the binary input number is 13, there will be 13 output pulses for every 16 input pulses.

The **HCC/HCF4089B** has an internal synchronous 4-bit counter which, together with one of the four binary input bits, produces pulse trains as shown in timing diagram.

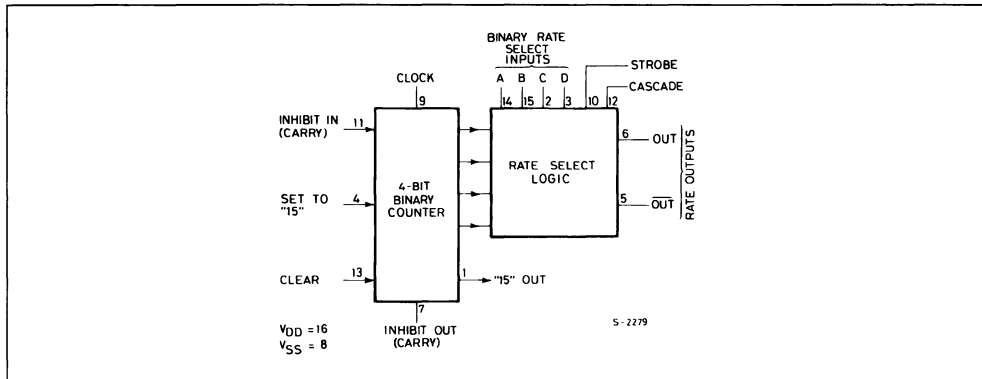
If more than one binary input bit is high, the resulting pulse train is a combination of the above separate pulse trains. This device may be used to perform arithmetic operations (add, subtract, divide, raise to a power), solve algebraic and differential equations, generate natural logarithms and trigonometric functions, A/D and D/A conversions, and frequency division.

PIN CONNECTIONS



5 - 2280

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage . HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

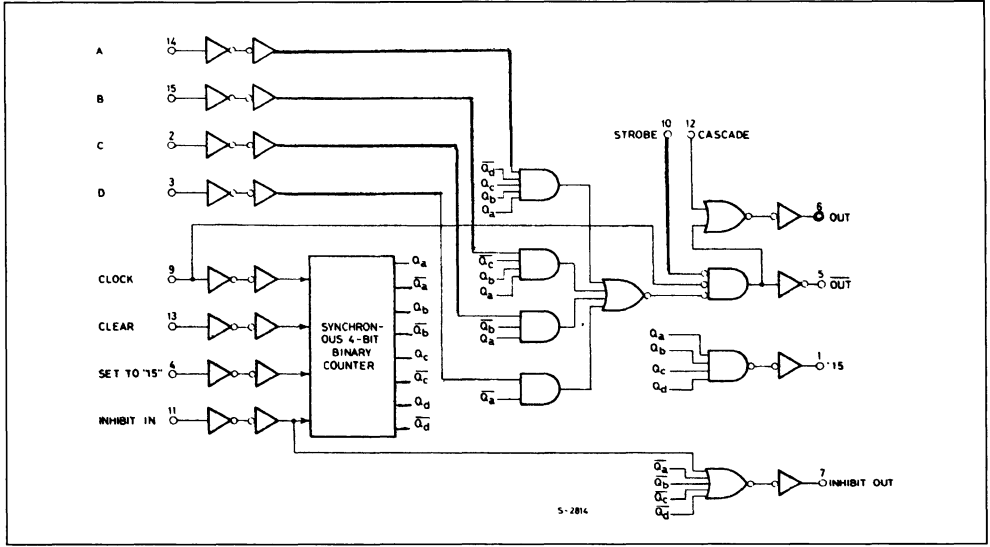
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



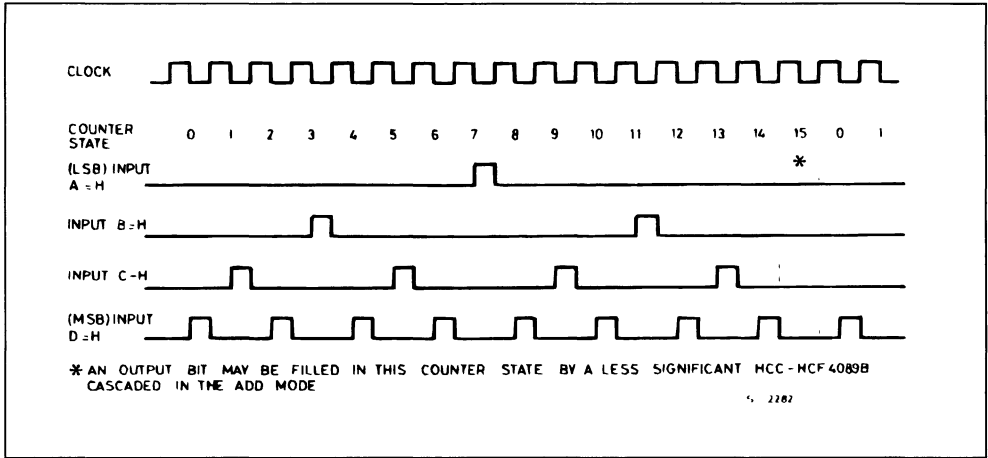
TRUTH TABLE

Inputs									Outputs				
Number of Pulses or Input Logic Level (0 = low ; 1 = high ; X = don't care)									Number of Pulses or Output Logic Level (L = low ; H = high)				
D	C	B	A	CLK	INH IN	STR	CAS	CLR	SET	OUT	OUT̄	INH OUT	"15" OUT
0	0	0	0	16	0	0	0	0	0	L	H	1	1
0	0	0	1	16	0	0	0	0	0	1	1	1	1
0	0	1	0	16	0	0	0	0	0	2	2	1	1
0	0	1	1	16	0	0	0	0	0	3	3	1	1
0	1	0	0	16	0	0	0	0	0	4	4	1	1
0	1	0	1	16	0	0	0	0	0	5	5	1	1
0	1	1	0	16	0	0	0	0	0	6	6	1	1
0	1	1	1	16	0	0	0	0	0	7	7	1	1
1	0	0	0	16	0	0	0	0	0	8	8	1	1
1	0	0	1	16	0	0	0	0	0	9	9	1	1
1	0	1	0	16	0	0	0	0	0	10	10	1	1
1	0	1	1	16	0	0	0	0	0	11	11	1	1
1	1	0	0	16	0	0	0	0	0	12	12	1	1
1	1	0	1	16	0	0	0	0	0	13	13	1	1
1	1	1	0	16	0	0	0	0	0	14	14	1	1
1	1	1	1	16	0	0	0	0	0	15	15	1	1
X	X	X	X	16	1	0	0	0	0	*	*	H	*
X	X	X	X	16	0	1	0	0	0	L	H	1	1
X	X	X	X	16	0	0	1	0	0	H	*	1	1
1	X	X	X	16	0	0	0	1	0	16	16	H	L
0	X	X	X	16	0	0	0	1	0	L	H	H	L
X	X	X	X	16	0	0	0	0	1	L	H	L	H

* Output same as the first 16 lines of this truth table (depending on values of A, B, C, D).

• Depends on internal state of counter.

TIMING DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5	0.04	5		150	μA
			0/10			10		10	0.04	10		300	
			0/15			15		20	0.04	20		600	
		HCF Types	0/20			20		100	0.08	100		3000	
			0/ 5			5		20	0.04	20		150	
			0/10			10		40	0.04	40		300	
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95			4.95		V	
		0/10	< 1	10	9.95		9.95			9.95			
		0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V	
		10/0	< 1	10		0.05			0.05		0.05		
		15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V	
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5		1.5		1.5	V	
			9/1	< 1	10		3		3		3		
			13.5/1.5	< 1	15		4		4		4		

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter		Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.		
t_{PHL} , t_{PLH}	Propagation Delay Time	Clock to out	5		110	220	ns	
			10		55	110		
			15		45	90		
		Clock or Strobe to out	5		150	300	ns	
			10		75	150		
			15		60	120		
		Clock to Inhibit High Level to Low Level	5		360	720	ns	
			10		160	320		
			15		110	220		
		Low Level to High Level	5		250	500	ns	
			10		100	200		
			15		75	150		
		Clear to out	5		380	760	ns	
			10		175	350		
			15		130	260		
		Clock to "9" or "15" out	5		300	600	ns	
			10		125	250		
			15		90	180		
		Cascade to out	5		90	180	ns	
			10		45	90		
			15		35	70		
		Inhibit in to Inhibit out	5		160	320	ns	
			10		75	150		
			15		55	110		
Set to out	5		330	660	ns			
	10		150	300				
	15		110	220				

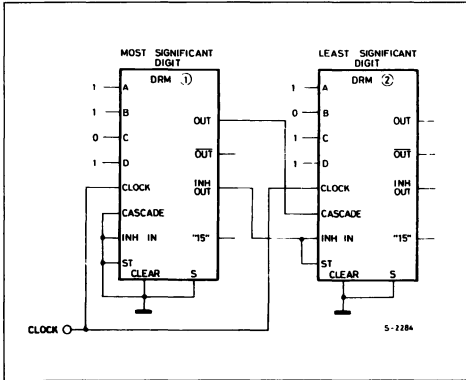
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
		V _{DD} (V)	Min.	Typ.	Max.		
t _{THL} , t _{TLH}	Transition Time	5		100	200	ns	
		10		50	100		
		15		40	80		
f _{CL}	Maximum Clock Frequency	5	1.2	2.4		MHz	
		10	2.5	5			
		15	3.5	7			
t _w	Clock Pulse Width	5	330	165		ns	
		10	170	85			
		15	100	50			
t _r , t _f	Clock Rise or Fall Time	5			15	μs	
		10			15		
		15			15		
t _w	Set or Clear Pulse Width	5	160	80		ns	
		10	90	45			
		15	60	30			
t _{setup}	Inhibit Input Setup Time, High Level to Low Level	5	100	50		ns	
		10	40	20			
		15	20	10			
t _R	Inhibit, Input Removal Time	5	240	120		ns	
		10	130	65			
		15	110	55			
t _R	Minimum Set Removal Time	5	150	75		ns	
		10	80	40			
		15	50	25			
t _R	Clear Removal Time	5	60	30		ns	
		10	40	20			
		15	30	15			

APPLICATION NOTES

For words of more than 4 bits, HCC/HCF4089B devices may be cascaded in two different modes : an Add mode and a Multiply mode.

Two HCC/HCF4089B's cascaded in the "Add" mode with a preset number of 189.

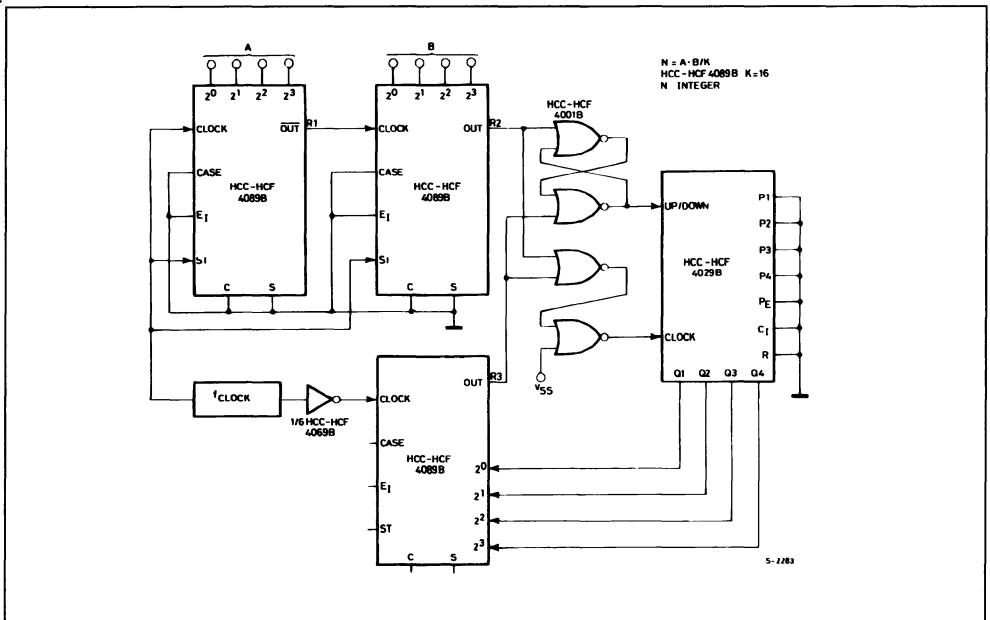


Nota :

In the Add mode some of the gaps left by the more significant unit at the count of 15 are filled in by the less significant units. For example, when two units are cascaded in the Add mode and programmed to 11 and 13, respectively, the more significant unit will have 11 output pulses for every 16 input pulses and the other unit will have 13 output pulses for every 256 input pulses for a total of

$$\frac{11}{16} + \frac{13}{256} = \frac{189}{256}$$

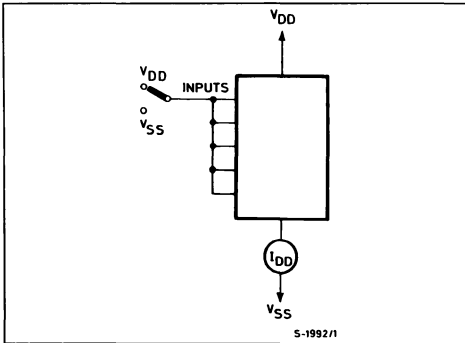
Two HCC/HCF4089B's cascaded in the Multiply mode for Multiplication of two variables A and B with loop circuit control.



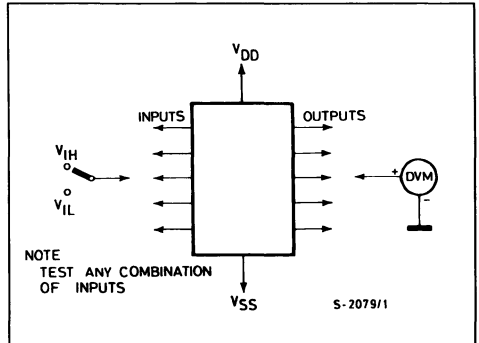
When the loop stabilises rate R2 = rate R3, thus $f_{clock} \left(\frac{A}{16} \cdot \frac{B}{16} \right) = f_{clock} \left(\frac{1}{16} \cdot \frac{N}{16} \right)$ therefore $N = A \cdot B$.

TEST CIRCUITS

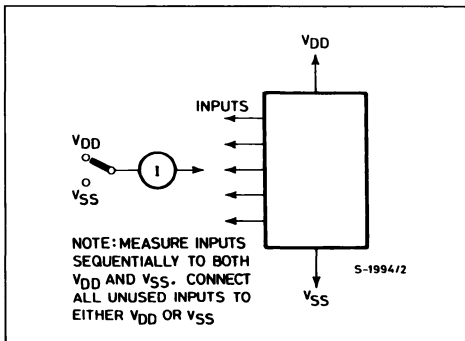
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.



QUAD 2-INPUT NAND SCHMIDT TRIGGERS

- SCHMITT-TRIGGER ACTION ON EACH INPUT WITH NO EXTERNAL COMPONENTS
- HYSTERESIS VOLTAGE TYPICALLY 0.9V AT $V_{DD} = 5V$ AND 2.3V AT $V_{DD} = 10V$
- NOISE IMMUNITY GREATER THAN 50% OF V_{DD} (typ.)
- NO LIMIT ON INPUT RISE AND FALL TIMES
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


EY
 (Plastic Package)

F
 (Ceramic Frit Seal Package)

M1
 (Micro Package)

C1
 (Plastic Chip Carrier)

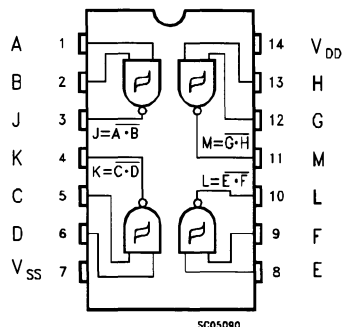
ORDER CODES :

HCC4093BF	HCF4093BM1
HCF4093BEY	HCF4093BC1

DESCRIPTION

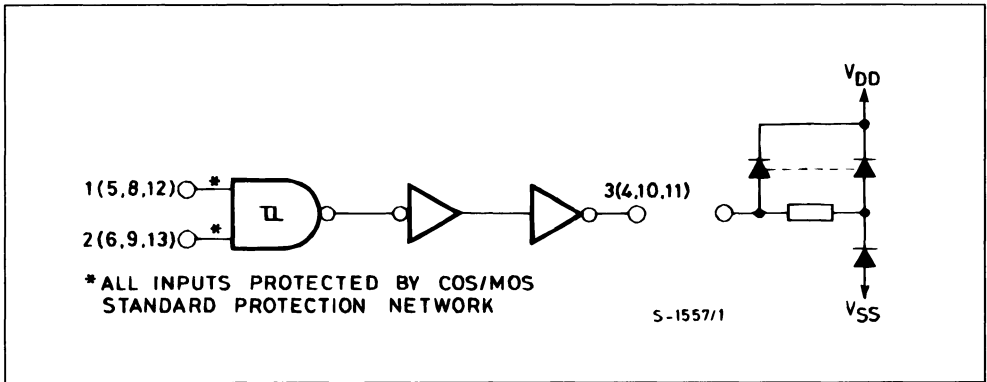
The **HCC4093B** (extended temperature range) and **HCF4093B** (intermediate temperature range) are available in 14-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4093B** consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals.

The difference between the positive voltage (V_P) and the negative voltage (V_N) is defined as hysteresis voltage (V_H) (see fig. 1).

PIN CONNECTIONS


FUNCTIONAL DIAGRAM

1 of 4 Schmitt triggers



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{Op} =$ Full Package-temperature Range	200 100	mW mW
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{Op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _P	Positive Trigger Threshold Voltage	a	5			5	2.2	3.6	2.2	2.9	3.6	2.2	3.6	V
			10			10	4.6	7.1	4.6	5.9	7.1	4.6	7.1	
			15			15	6.8	10.8	6.8	8.8	10.8	6.8	10.8	
			b			5	2.6	4	2.6	3.3	4	2.6	4	
			10			10	5.6	8.2	5.6	7	8.2	5.6	8.2	
			15			15	6.3	12.7	6.3	9.4	12.7	6.3	12.7	
V _N	Negative Trigger Threshold Voltage	a	5			5	0.9	2.8	0.9	1.9	2.8	0.9	2.8	V
			10			10	2.5	5.2	2.5	3.9	5.2	2.5	5.2	
			15			15	4	7.4	4	5.8	7.4	4	7.4	
			b			5	1.4	3.2	1.4	2.3	3.2	1.4	3.2	
			10			10	3.4	6.6	3.4	5.1	6.6	3.4	6.6	
			15			15	4.8	9.6	4.8	7.3	9.6	4.8	9.6	
			b			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	
V _H	Hysteresis Voltage	a	10			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4	V
			15			15	1.6	5	1.6	3.5	5	1.6	5	
			b			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	
			10			10	1.2	3.4	1.2	2.3	3.4	1.2	3.4	
			15			15	1.6	5	1.6	3.5	5	1.6	5	
			b			5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	
V _{OH}	Output High Voltage		0/5		< 1	5	4.95		4.95			4.95	V	
			0/10		< 1	10	9.95		9.95			9.95		
			0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage		5/0		< 1	5		0.05			0.05	0.05	V	
			10/0		< 1	10		0.05			0.05	0.05		
			15/0		< 1	15		0.05			0.05	0.05		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					

a : input on terminals 1, 5, 8, 12 or 2, 6, 9, 13 ; other inputs to V_{DD}.b : input on terminals 1 and 2, 5 and 6, 8 and 9, or 12 and 13 ; other inputs to V_{DD}.* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

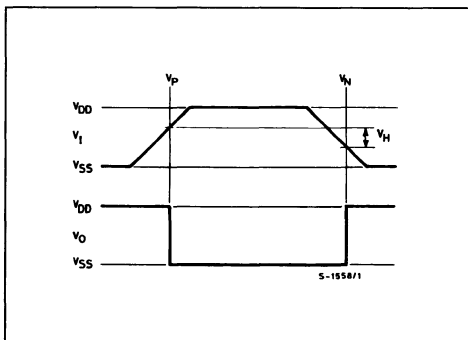
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OL}	Output Sink Current		0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
			0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	± 10 ⁻⁵	± 0.1		± 1	μA	
		HCF Types	0/15											15
C _I	Input Capacitance			Any Input					5	7.5			pF	

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200kΩ, typical temperature coefficient for all V_{DD} = 0.3%/°C values , all input rise and fall time = 20ns)

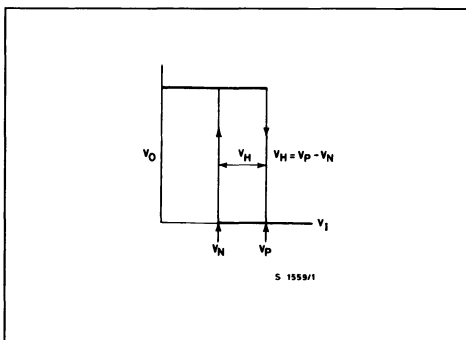
Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time		5		190	380	ns
			10		90	180	
			15		65	130	
t _{TLH} , t _{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

Figure 1 : Hysteresis Definition, Characteristics and Test Setup.

(a) Definition of V_P, V_N and V_H



(b) Transfer characteristics of 1 of 4 gates



(c) Test setup

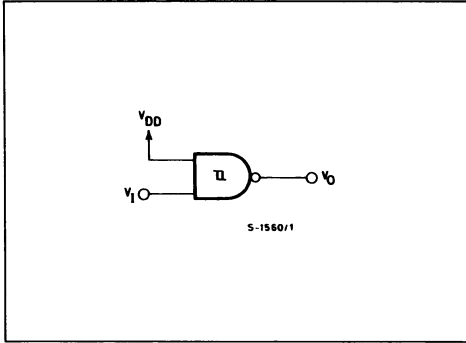


Figure 2 : Input and Output Characteristics.

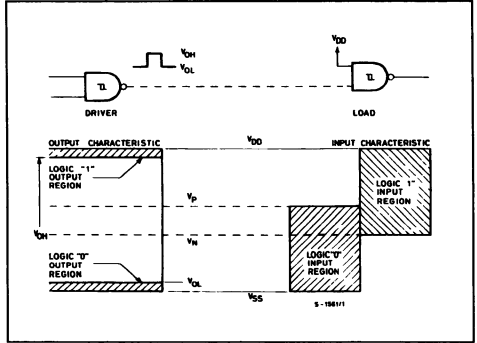


Figure 3 : Typical Current and Voltage Transfer Characteristics.

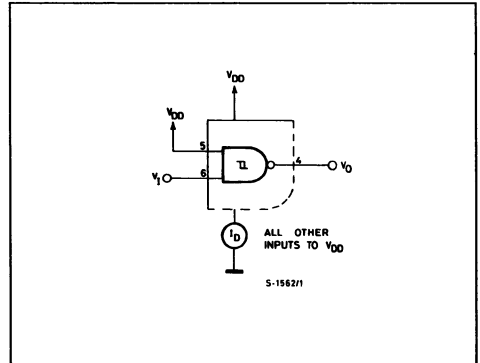
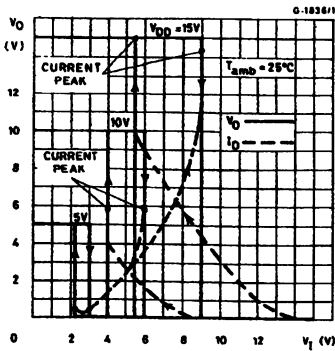


Figure 4 : Typical Voltage Transfer Characteristics as a Function of Temperature, and Test Circuit.

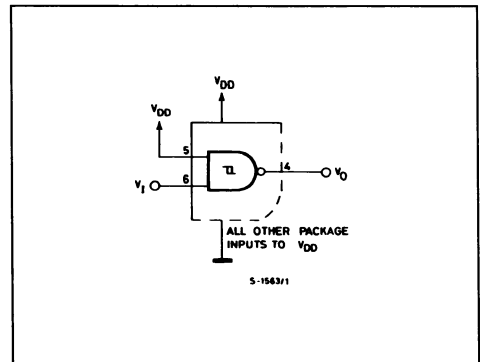
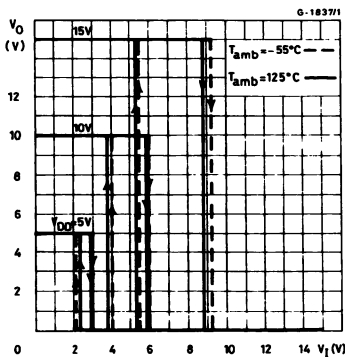


Figure 5 : Typical Output Low (sink) Current Characteristics.

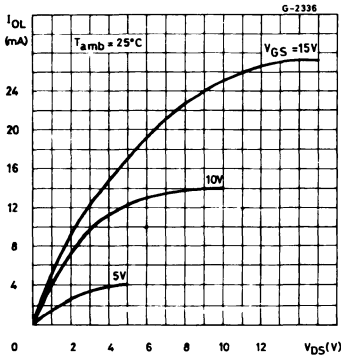


Figure 6 : Minimum Output Low (sink) Current Characteristics.

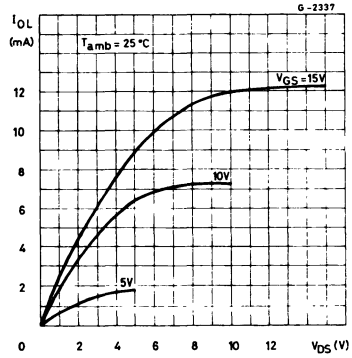


Figure 7 : Typical Output High (source) Current Characteristic.

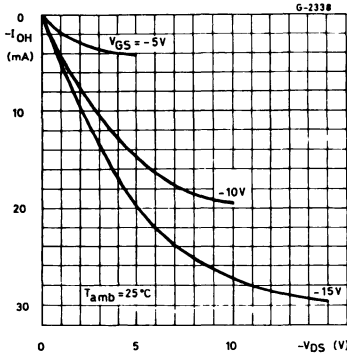


Figure 8 : Minimum Output High Current Characteristics.

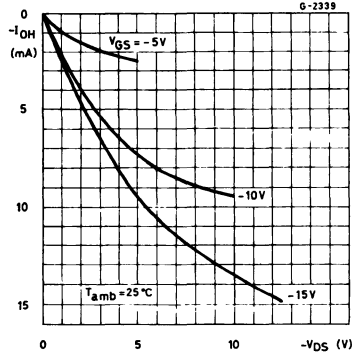


Figure 9 : Typical Propagation Delay Time vs. Supply Voltage.

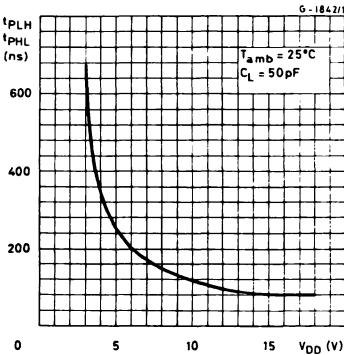


Figure 10 : Typical Transition Time vs. Load Capacitance.

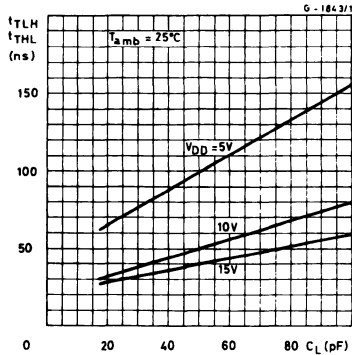


Figure 11 : Typical Trigger Threshold Voltage vs. V_{DD}

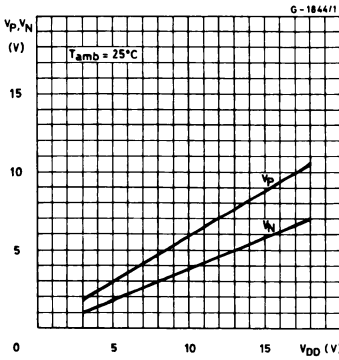


Figure 12 : Typical per cent Hysteresis vs. Supply Voltage.

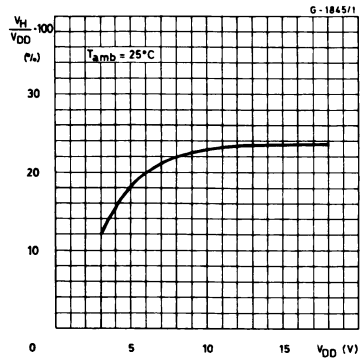


Figure 13 : Typical Dissipation Characteristics.

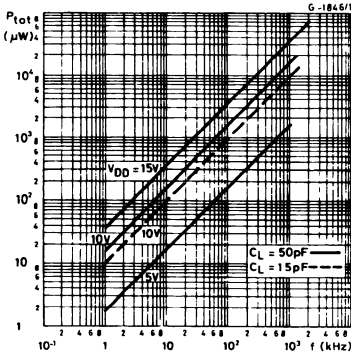
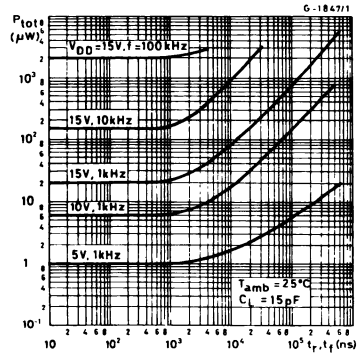


Figure 14 : Power Dissipation vs. Rise and Fall Times.



APPLICATIONS

Figure 15 : Wave Shaper.

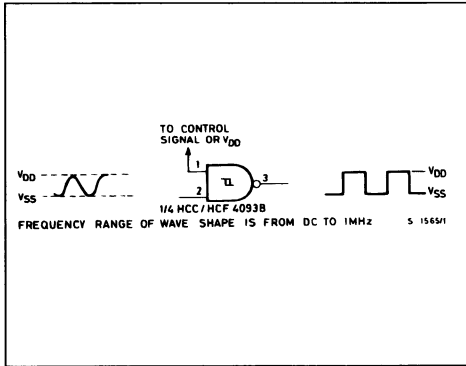


Figure 16 : Monostable Multivibrator.

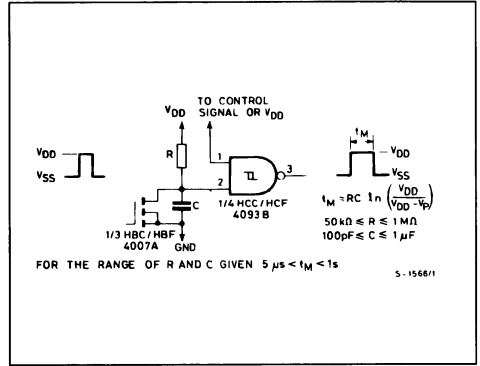
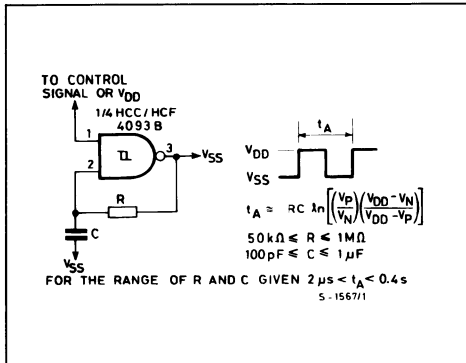


Figure 17 : Astable Multivibrator.



TEST CIRCUITS

Figure 18 : Quiescent Device Current.

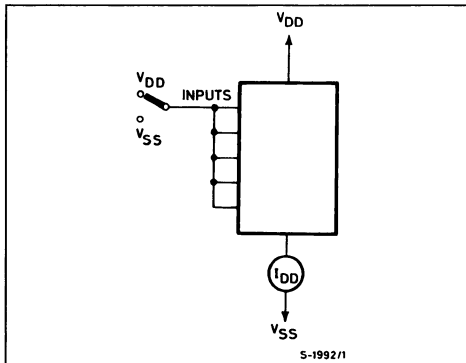
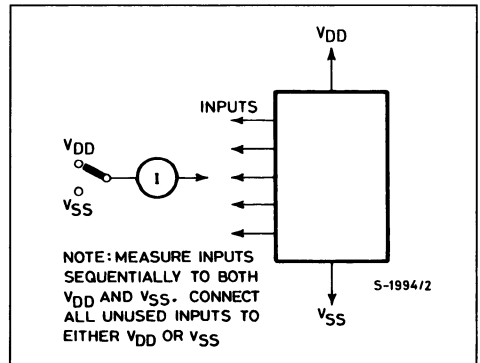
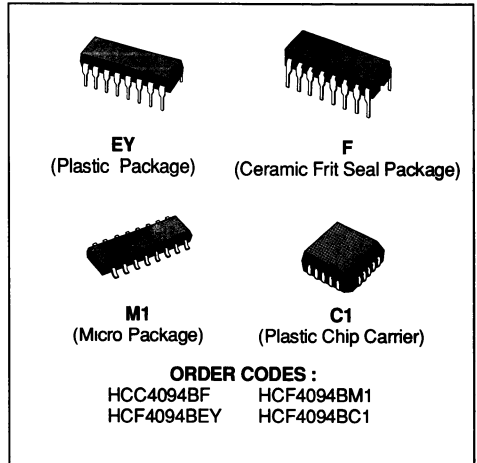


Figure 19 : Input Leakage Current.



8-STAGE SHIFT-AND-STORE BUS REGISTER

- 3-STATE PARALLEL OUTPUTS FOR CONNECTION TO COMMON BUS
- SEPARATE SERIAL OUTPUTS SYNCHRONOUS TO BOTH POSITIVE AND NEGATIVE CLOCK EDGES FOR CASCADING
- MEDIUM SPEED OPERATION 5MHz AT 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

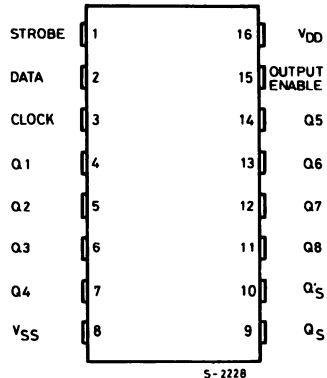


DESCRIPTION

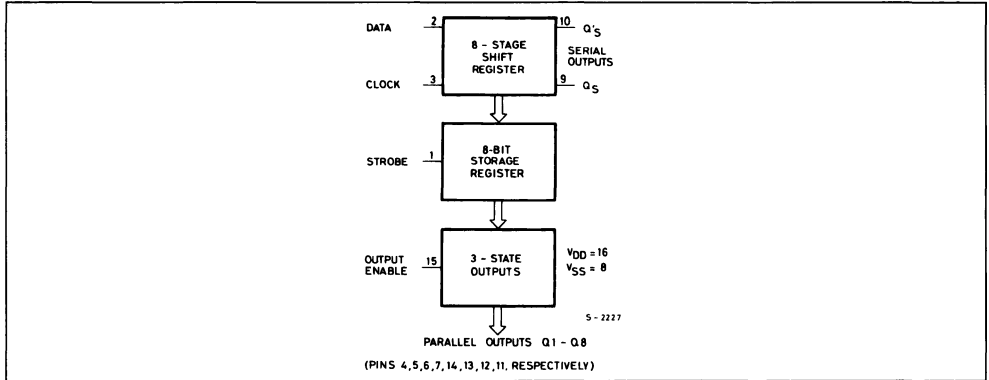
The **HCC4094B** (extended temperature range) and **HCF4094B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4094B** is an 8-stage serial shift register having a storage latch associated with each stage for strobing data from the serial input to parallel buffered 3-state outputs. The parallel outputs may be connected directly to common bus lines. Data is shifted on positive clock transitions. The data in each shift register stage is transferred to the storage register when the STROBE input is high. Data in the storage register appears at the outputs whenever the OUTPUT-ENABLE signal is high. Two serial outputs are available for cascading a number of **HCC/HCF4094B** devices. Data is available at the Q_5 serial output terminal on positive clock edges to allow for high-speed operation in cascaded systems in which the clock rise time is fast. The same serial information, available at the Q' 's terminal on the next negative clock edge, provides a means for cascading **HCC/HCF4094B** devices when the clock rise time is slow.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

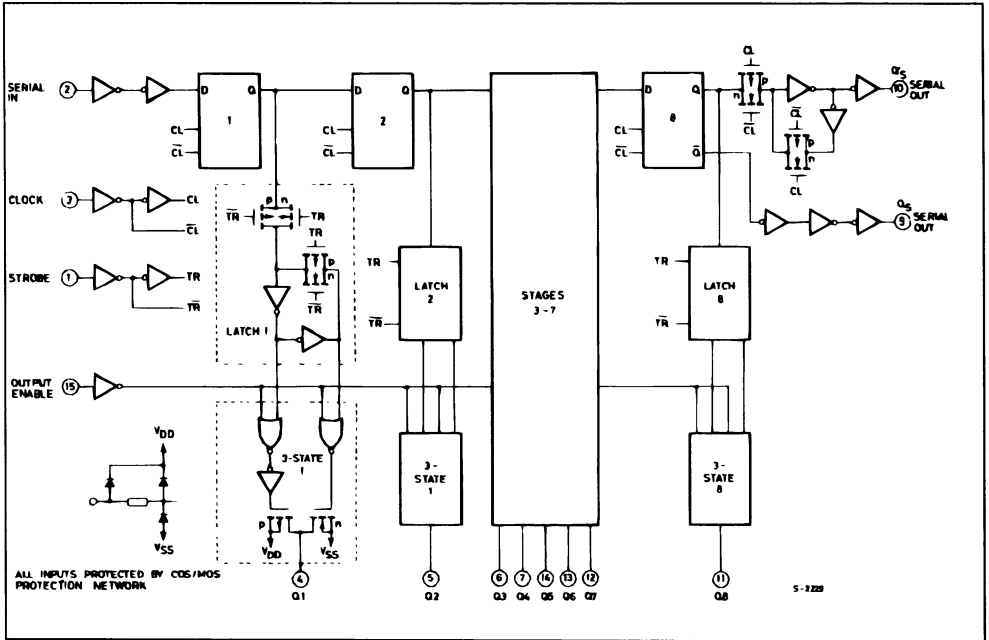
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

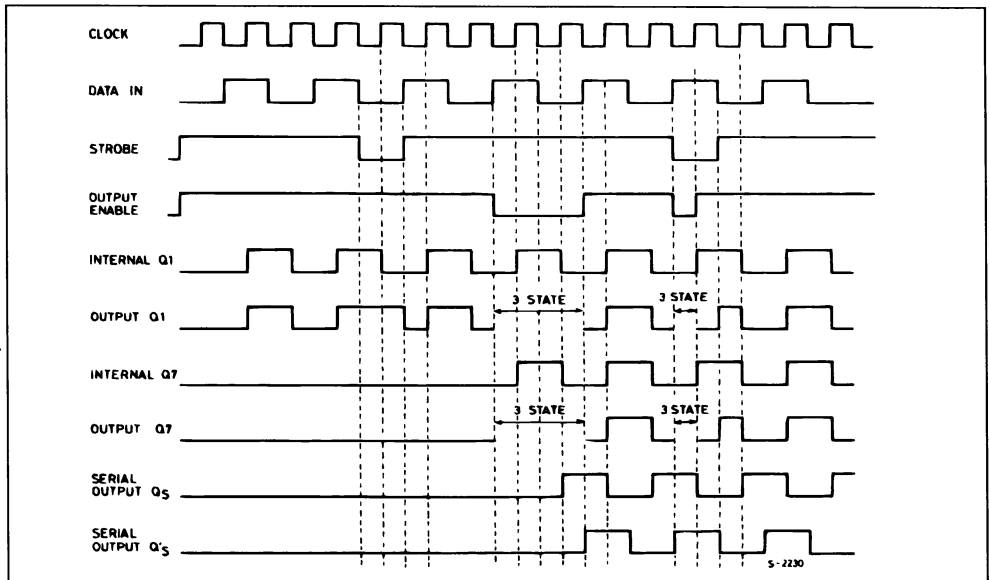
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS









TIMING DIAGRAM



TRUTH TABLE

TRUTH TABLE

CL ^Δ	Outputs Enable	Strobe	Data	Parallel Outputs		Serial Outputs	
				Q1	QN	QS*	Q'S
	0	X	X	OC	OC	Q7	NC
	0	X	X	OC	OC	NC	Q7
	1	0	X	NC	NC	Q7	NC
	1	1	0	0	Q _{N-1}	Q7	NC
	1	1	1	1	Q _{N-1}	Q7	NC
	1	1	1	NC	NC	NC	Q7

▲ = Level Change
 X = Don't Care
 NC = No Change
 OC = Open Circuit

Logic 1 ≡ High
 Logic 0 ≡ Low

* At the positive clock edge information in the 7th shift register stage is transferred to the 8th register stage and the Q_s output

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

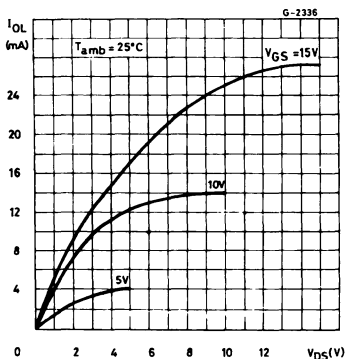
Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/5	< 1		5	4.95		4.95			4.95			V
		0/10	< 1		10	9.95		9.95			9.95			
		0/15	< 1		15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1		5		0.05			0.05		0.05	V	
		10/0	< 1		10		0.05			0.05		0.05		
		15/0	< 1		15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
		0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15											15
I _{OH} , I _{OL}	3-state Output Leakage Current	HCC Types	0/18	0/18	18		± 0.4		$\pm 10^{-4}$	± 0.4		± 12	μ A	
		HCF Types	0/15	0/15	15		± 1.0		$\pm 10^{-4}$	± 1.0		± 7.5	μ A	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = -55°C for HCC device : -40°C for HCF device* T_{High} = +125°C for HCC device : +85°C for HCF deviceThe Noise Margin for both "1" and "0" level is .1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

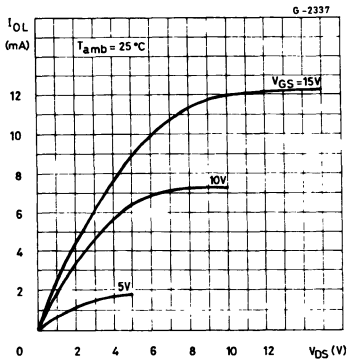
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values , all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL}	Propagation Delay Time Clock to Serial Output Q_S		5		300	600	ns
			10		125	250	
			15		95	190	
t_{PLH}, t_{PHL}	Propagation Delay Time Clock to Serial Output Q'_S		5		230	460	ns
			10		110	220	
			15		75	150	
t_{PLH}, t_{PHL}	Propagation Delay Time Clock to Parallel Output		5		420	840	ns
			10		195	390	
			15		135	270	
t_{PLH}, t_{PHL}	Propagation Delay Time Strobe to Parallel Output		5		290	580	ns
			10		145	290	
			15		100	200	
t_{PHZ}	Propagation Delay Time Output Enable to Parallel Output : Output High to High Impedance		5		140	280	ns
			10		75	150	
			15		55	110	
t_{PLZ}	Out Low to High Impedance		5		225	450	ns
			10		95	190	
			15		70	140	
t_w	Strobe Pulse Width		5	200	100		ns
			10	80	40		
			15	70	35		
t_w	Clock Pulse Width		5	200	100		ns
			10	100	50		
			15	83	40		
t_{setup}	Data Setup Time		5	125	60		ns
			10	55	30		
			15	35	20		
t_{TLH}, t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_r, t_f	Clock Input Rise or Fall Time		5	15			μs
			10	5			
			15	5			
f_{max}	Maximum Clock Input Frequency		5	1.25	2.5		MHz
			10	2.5	5		
			15	3	6		

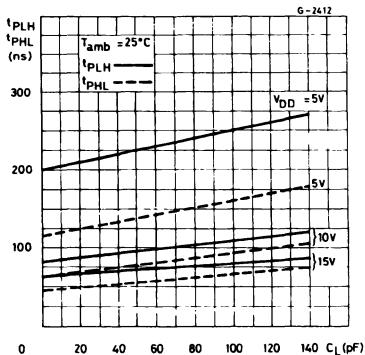
Typical Output Low (sink) Current Characteristics.



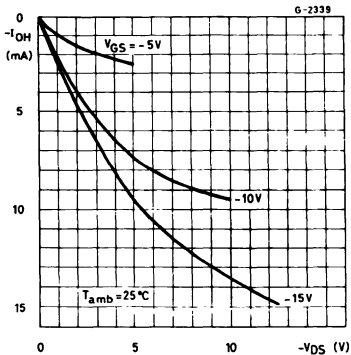
Minimum Output Low (sink) Current Characteristics.



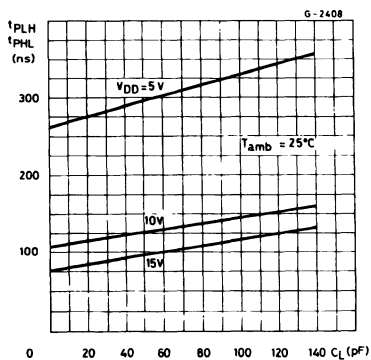
Typical Output High (source) Current Characteristics.



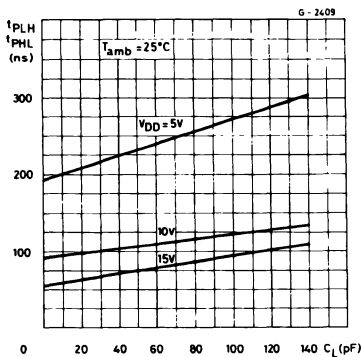
Minimum Output High (source) Current Characteristics.



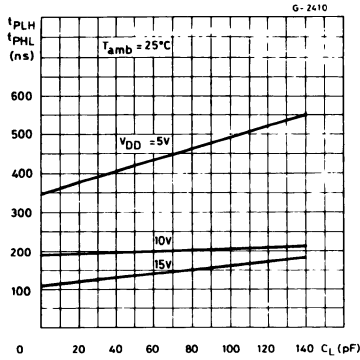
Clock-to-serial Output Qs Propagation Delay vs. CL.



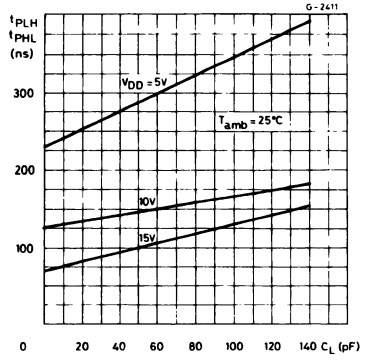
Clock-to-serial Output Q's Propagation Delay vs. CL.



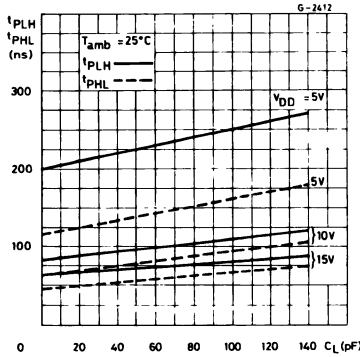
Clock-to-parallel Output Propagation Delay vs. C_L .



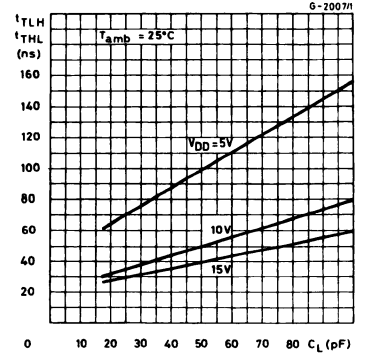
Strobe-to-parallel Output Propagation Delay vs. C_L .



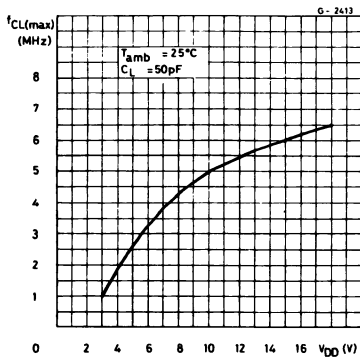
Output Enable-to-parallel Output Propagation Delay vs.



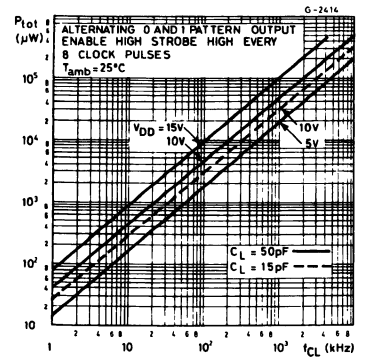
Typical Transition Time vs. Load Capacitance.



Typical Maximum-clock Frequency vs. Supply Voltage.

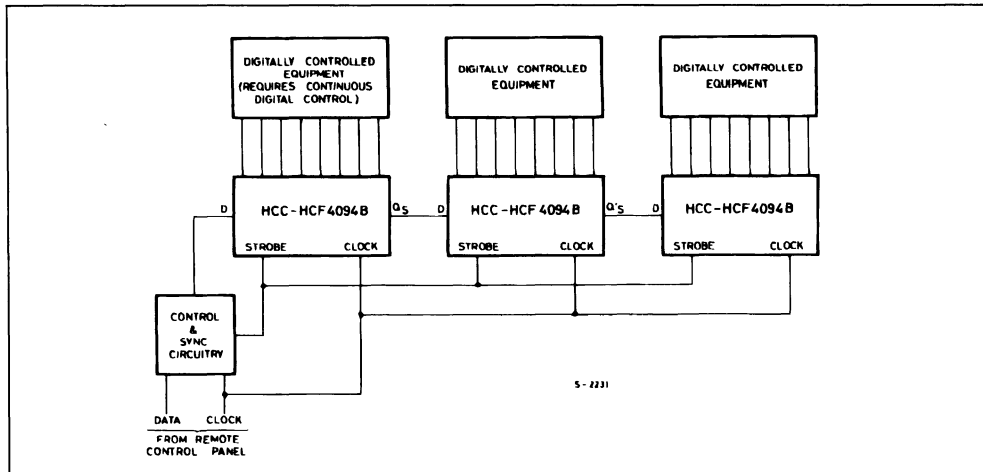


Dynamic Power Dissipation vs. Input Clock Frequency.



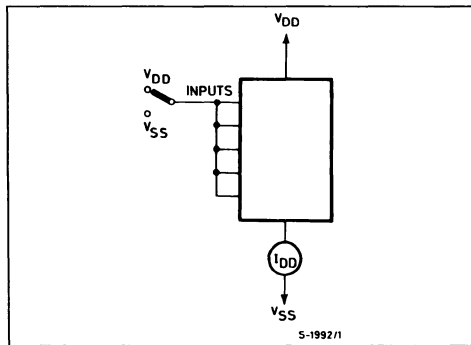
TYPICAL APPLICATION

REMOTE CONTROL HOLDING REGISTER

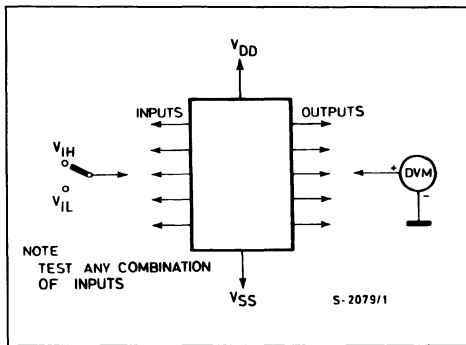


TEST CIRCUITS

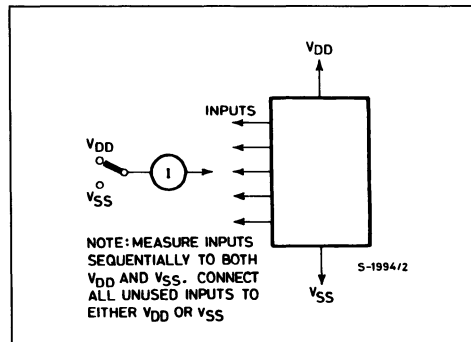
Quiescent Device Current.

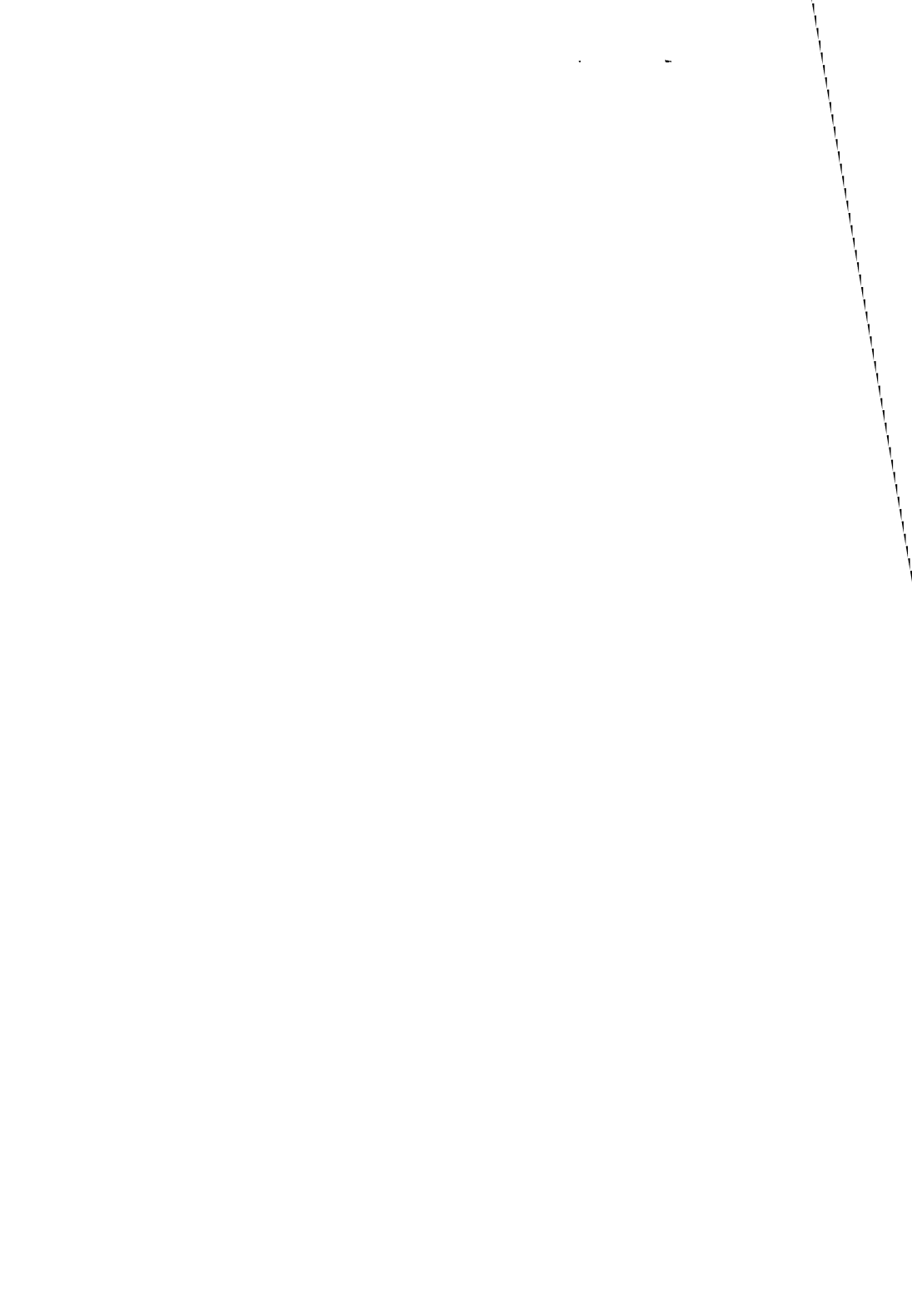


Noise Immunity.



Input Leakage Current.





GATE J-K MASTER-SLAVE FLIP-FLOPS

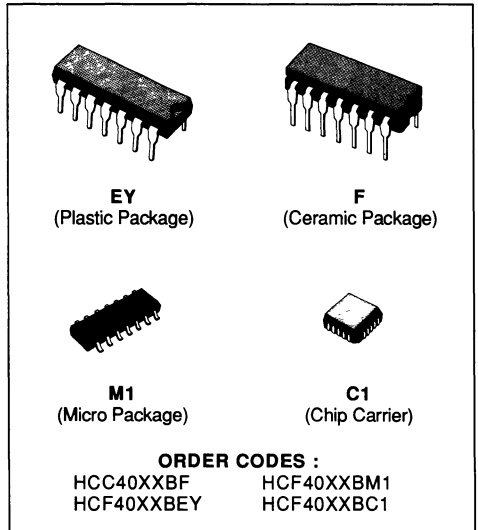
- 16 MHz TOGGLE RATE (typ.) AT $V_{DD} - V_{SS} = 10V$
- GATED INPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 250C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No 13 A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

inputs is transferred to the Q and \bar{Q} outputs on the positive edge of the clock pulse. SET and RESET inputs (active high) are provided for asynchronous operation.

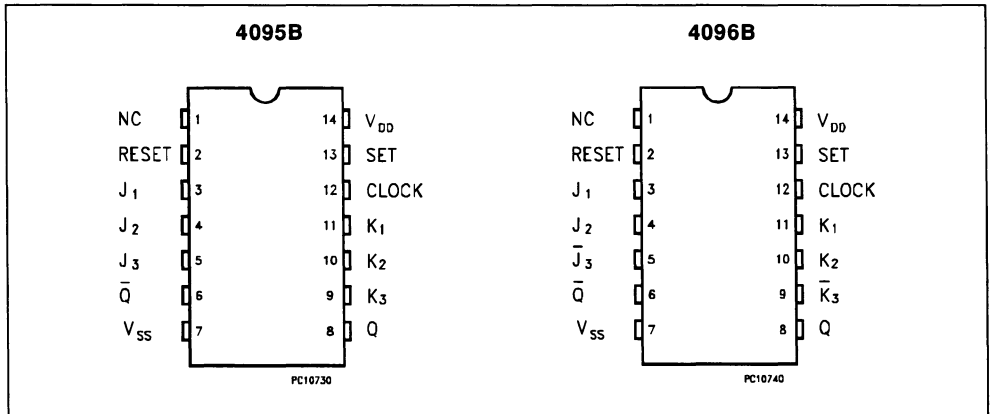
DESCRIPTION

The **HCC4095B/4096B** (extended temperature range) and **HCF4095B/4096B** (intermediate temperature range) are monolithic integrated circuits, available in 14 lead dual in-line plastic or ceramic package and plastic micropackage.

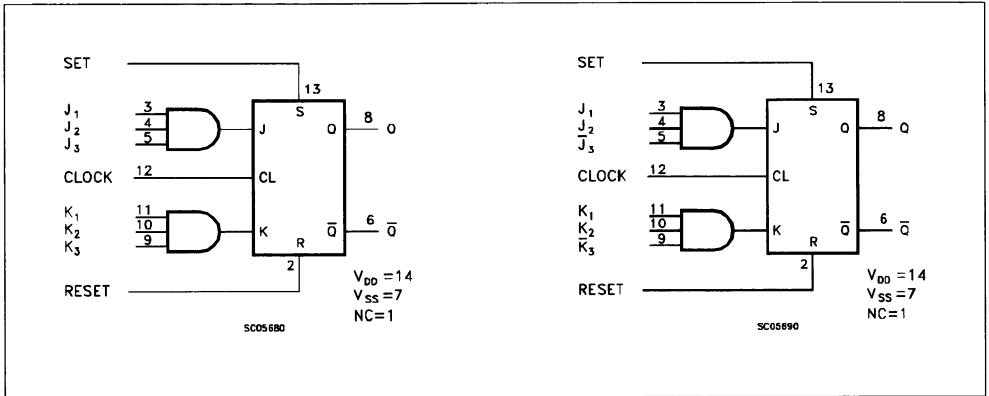
The **HCC/HCF4095B** and **HCC/HCF4096B** are J-K Master-Slave Flip-Flops featuring separate AND gating of multiple J and K inputs. The gated J-K input control transfer of information into the master section during clocked operation. Information on the J-K



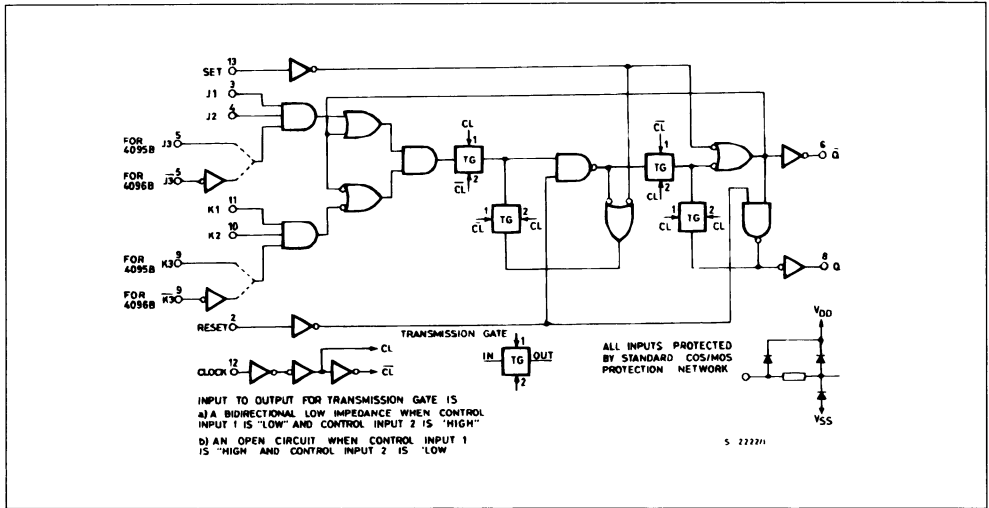
PIN CONNECTIONS



FUNCTIONAL DIAGRAMS



LOGIC DIAGRAM



TRUTH TABLES

SYNCHRONOUS OPERATION (S=0 R=0)

Inputs Before Positive Clock Transition		Outputs After Positive Clock Transition	
J *	K *	Q	Q̄
0	0	No Change	
0	1	0	1
1	0	1	0
1	1	Toggles	

* For 4095B J = J1 · J2 · J3, K = K1 · K2 · K3

* For 4096B J = J1 · J2 · J3, K = K1 · K2 · K3

ASYNCHRONOUS OPERATION (J and K DON'T CARE)

S	R	Q	Q̄
0	0	No Change	
0	1	0	1
1	0	1	0
1	1	0	0

0 = Vss, 1 = VDD

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20	V
		-0.5 to +18	V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95			V	
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V	
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		4.5	< 1	5	3.5		3.5			3.5		V	
			9	< 1	10	7		7			7			
			13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		0.5	< 1	5		1.5			1.5		1.5	V	
			1	< 1	10		3			3		3		
			1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
		HCF Types	0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
			0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	0/18	Any Input			18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1	\pm 1	μ A	
		0/15	Any Input			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3	\pm 1		
C _i	Input Capacitance	Any Input							5	7.5		pF		

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

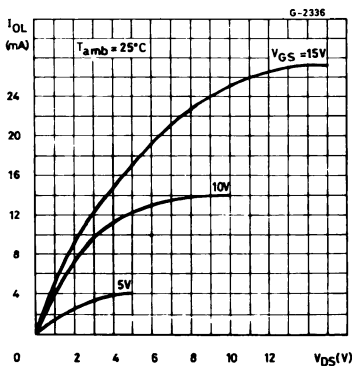
* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

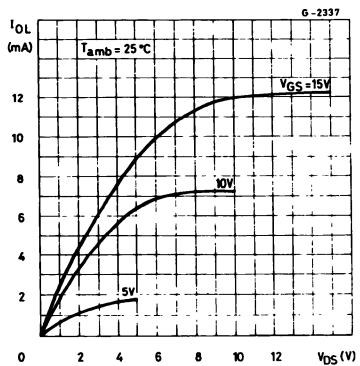
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time		5		250	500	ns
			10		100	200	
			15		75	150	
t_{PLH} t_{PHL}	Propagation Delay Time (Set or Reset)		5		150	300	ns
			10		75	150	
			15		50	100	
t_{THL} t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}	Maximum Clock Input Frequency		5	3.5	7		MHz
			10	8	16		
			15	12	24		
t_w	Clock Pulse Width		5	140	70		ns
			10	60	30		
			15	40	20		
t_r t_f	Clock Input Rise or Fall Time		5			15	μs
			10			5	
			15			5	
t_w	Set or Reset Pulse Width		5	200	100		ns
			10	100	50		
			15	50	25		
t_{setup}	Data Setup Time		5	400	200		ns
			10	160	80		
			15	100	50		

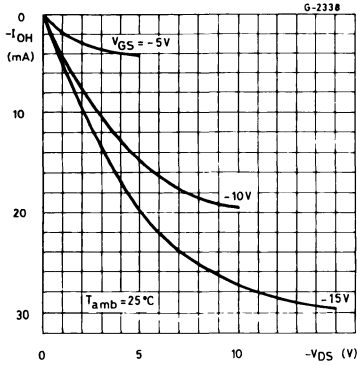
Typical Output Low (sink) Current Characteristics



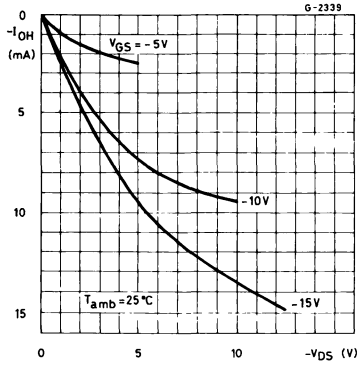
Minimum Output low (sink) Current Characteristics



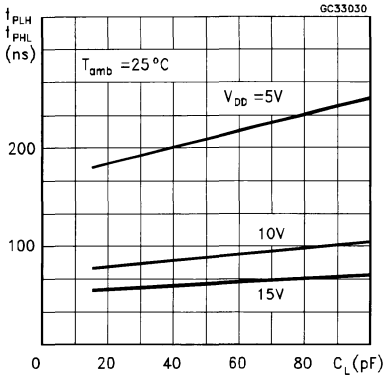
Typical Output High (source) Current Characteristics



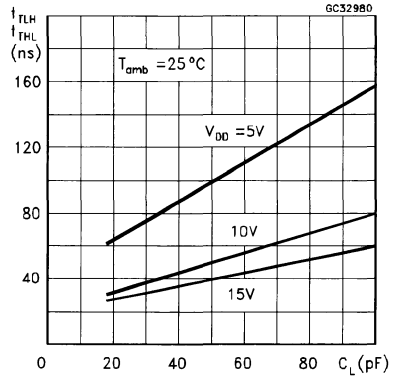
Minimum Output High (source) Current Characteristics



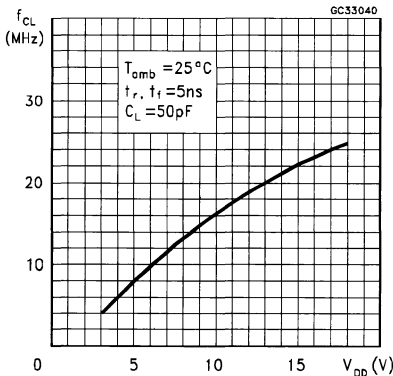
Typical Propagation Delay Time vs Load Capacitance



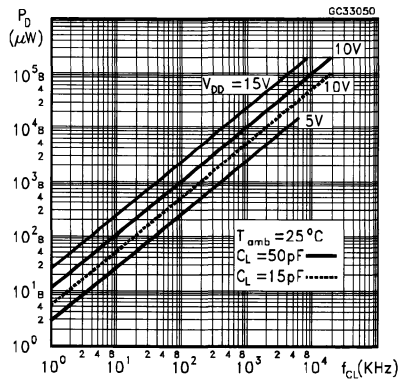
Typical Transition Time vs Load Capacitance



Typical Clock Frequency vs Supply Voltage (Toggle Mode)

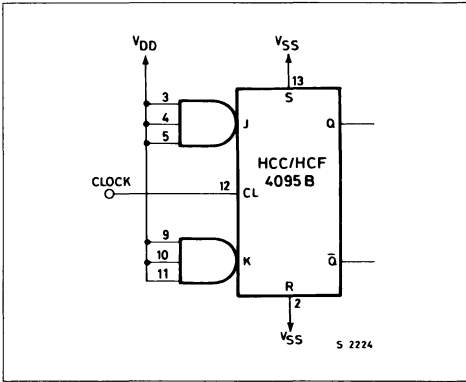


Typical Power Power Dissipation Vs. Input Clock Frequency

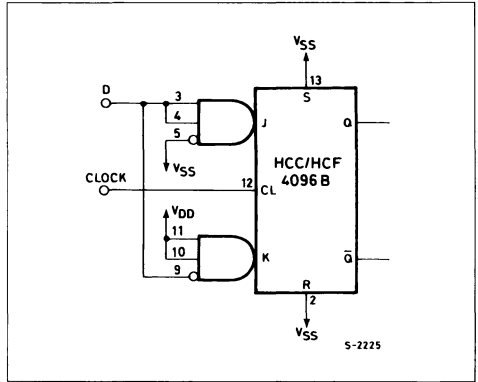


TYPICAL APPLICATIONS

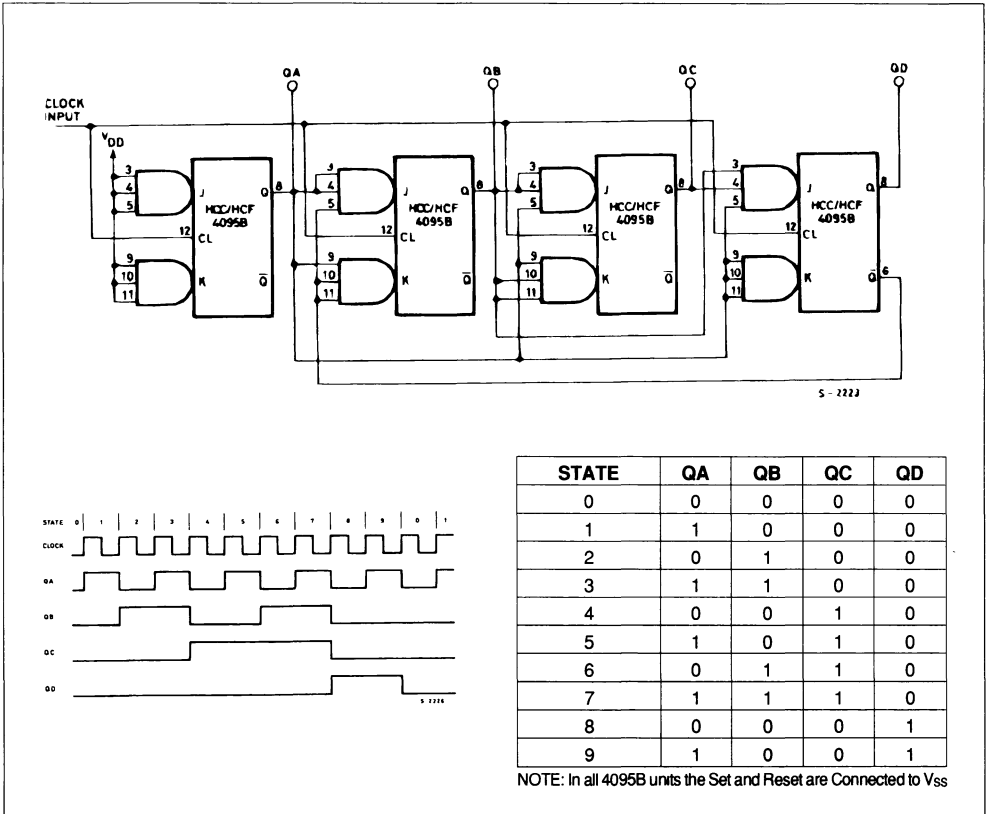
T-type Flip-Flop



D-type Flip-Flop

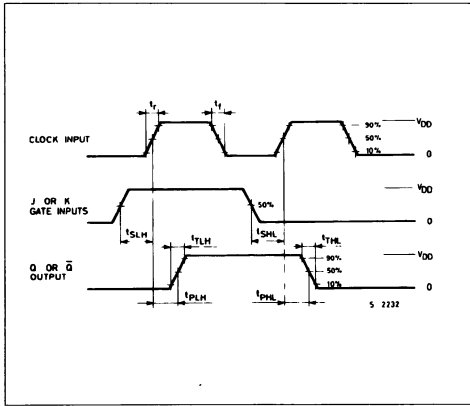


Synchronous Binary Divide by Ten Counter

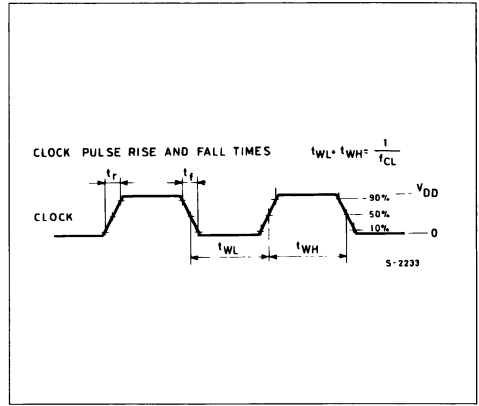


WAVEFORMS

Propagation Delay, Transition and Setup Time

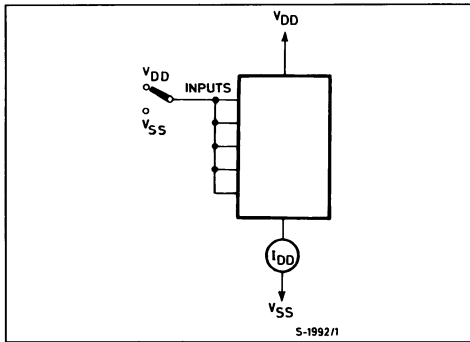


Clock Pulse Rise and Fall Time

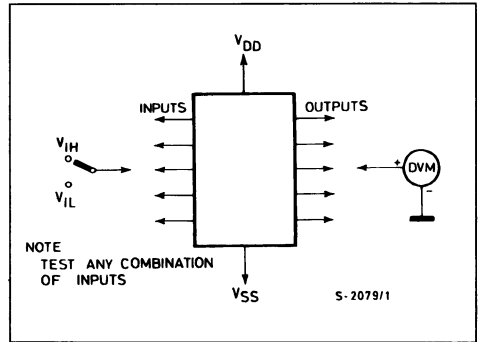


TEST CIRCUITS

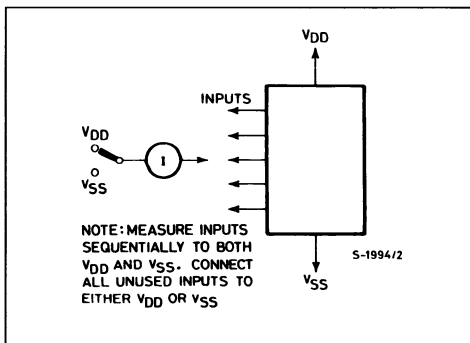
Quiescent Device Current.



Noise Immunity.

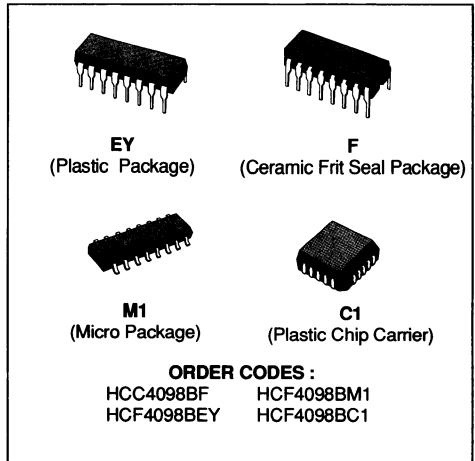


Input Leakage Current.



DUAL MONOSTABLE MULTIVIBRATOR

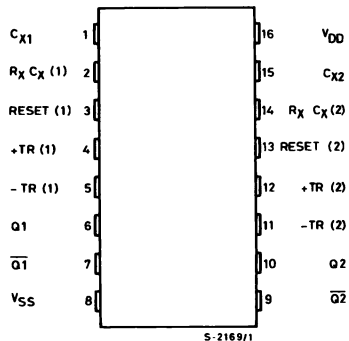
- RETRIGGERABLE/RESETTABLE CAPABILITY
- TRIGGER AND RESET PROPAGATION DELAYS INDEPENDENT OF R_X , C_X
- TRIGGERING FROM LEADING OR TRAILING EDGE
- Q AND \bar{Q} BUFFERED OUTPUTS AVAILABLE
- SEPARATE RESETS
- WIDE RANGE OF OUTPUT-PULSE WIDTHS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC4098B** (extended temperature range) and **HCF4098B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF4098B** dual monostable multivibrator provides stable retriggerable/resettable one-shot operation for any fixed-voltage timing application. An external resistor (R_X) and an external capacitor (C_X) control the timing for the circuit. Adjustment of R_X and C_X provides a wide range of output pulse widths from the Q and \bar{Q} terminals. The time delay from trigger input to output transition (trigger propagation delay) and the time delay from reset input to output transition (reset propagation delay) are independent of R_X and C_X . Leading-edge-triggering (+ TR) and trailing-edge-triggering (- TR) inputs are provided for triggering from either edge of an input pulse. An unused + TR input should be tied to V_{DD} . A RESET (on low level) is provided for immediate termination of the output pulse or to prevent output pulses when power is turned on. An unused RESET input should be tied to V_{DD} . However, if an entire section of the **4098B** is not used, its RESET should be tied to V_{SS} . See table I. In normal operation the circuit triggers (ex-

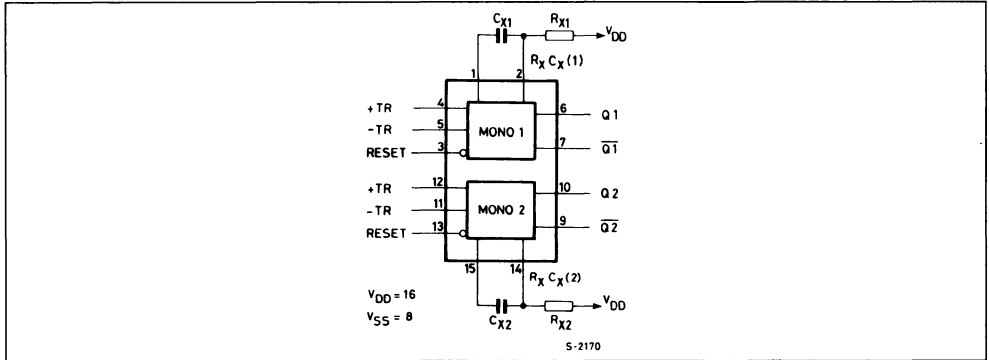
PIN CONNECTIONS



tends the output pulse one period) on the application of each new trigger pulse. For operation in the non-triggerable mode, Q is connected to -TR when leading-edge triggering (+ TR) is used or Q is connected to + TR when trailing-edge triggering (- TR) is used. The time period (T) for this multivibrator can be approximated by $T_X = 1/2 R_X C_X$ for $C_X \geq 0.01 \mu F$. Time periods as a function of R_X for values of C_X and V_{DD} are given in fig. 8. Values of T vary from unit to unit and as a function of voltage, temperature, and $R_X C_X$. The minimum value of external resistance, R_X , is 5 k Ω . The

maximum value of external capacitance, C_X , is 100 μF . Fig.9 shows time periods as a function of C_X for values of R_X and V_{DD} . The output pulse width has variations of $\pm 2.5\%$ typically, over the temperature range of $-55^\circ C$ to $125^\circ C$ for $C_X = 1000 pF$ and $R_X = 100 k\Omega$. For power supply variations of $\pm 5\%$, the output pulse width has variations of $\pm 0.5\%$ typically, for $V_{DD} = 10V$ and $15V$ and $\pm 1\%$ typically, for $V_{DD} = 5 V$ at $C_X = 1000 pF$ and $R_X = 5k\Omega$.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200	mW
		100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	$^\circ C$
		- 40 to + 85	$^\circ C$
T_{stg}	Storage Temperature	- 65 to + 150	$^\circ C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	$^\circ C$
		- 40 to + 85	$^\circ C$

LOGIC DIAGRAMS

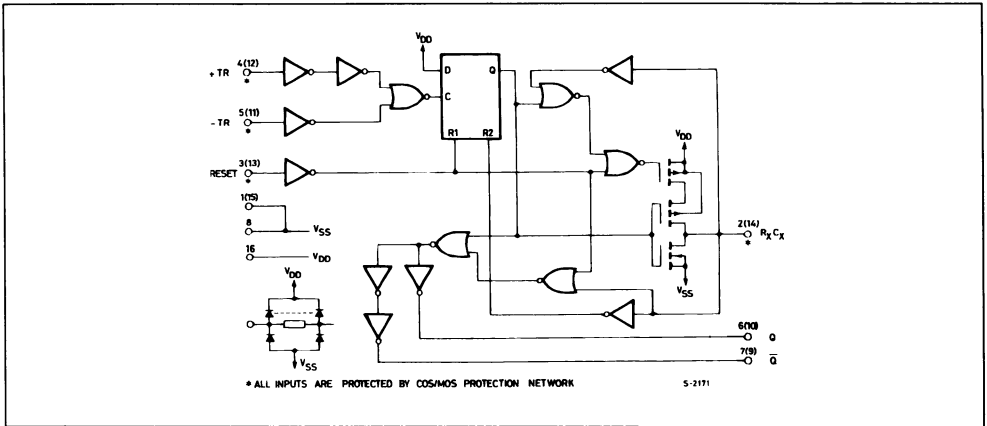
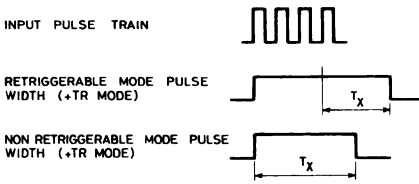


Table 1 : Functional Terminal Connections.

Function	Terminal Connections						Other Connections	
	to V _{DD}		to V _{SS}		Input Pulse to		Mono (1)	Mono (2)
	Mono (1)	Mono (2)	Mono (1)	Mono (2)	Mono (1)	Mono (2)		
Leading - Edge Trigger/Retriggerable	3,5	11,13			4	12		
Leading - Edge Trigger/Non - retriggerable	3	13			4	12	5,7	11,9
Trailing - Edge Trigger/Retriggerable	3	13	4	12	5	11		
Trailing - Edge Trigger/Non - retriggerable	3	13			5	11	4,6	12,10
Unused Section	5	11	3,4	12,13				

Notes : 1. A Retriggerable one-shot multivibrator has an output pulse width which is extended one full time period (T_x) after application of the last trigger pulse.
 2. A non-retriggerable one-shot multivibrator has a time period T_x referenced from the application of the first trigger pulse.



5-2172

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
V _{OH}	Output High Voltage		0/ 5	< 1	5	4.95		4.95			4.95		V	
			0/10	< 1	10	9.95		9.95			9.95			
			0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage		5/0	< 1	5		0.05			0.05		0.05	V	
			10/0	< 1	10		0.05			0.05		0.05		
			15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5	5	- 2		- 1.6	- 3.2		- 1.15		mA	
			0/ 5	4.6	5	- 0.64		- 0.51	- 1		- 0.36			
			0/10	9.5	10	- 1.6		- 1.3	- 2.6		- 0.9			
			0/15	13.5	15	- 4.2		- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5	5	- 1.53		- 1.36	- 3.2		- 1.1			
			0/ 5	4.6	5	- 0.52		- 0.44	- 1		- 0.36			
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4	5	0.64		0.51	1		0.36		mA	
			0/10	0.5	10	1.6		1.3	2.6		0.9			
			0/15	1.5	15	4.2		3.4	6.8		2.4			
			HCF Types	0/ 5	0.4	5	0.52		0.44	1		0.36		
		0/10		0.5	10	1.3		1.1	2.6		0.9			
		0/15	1.5	15	3.6		3.0	6.8		2.4				
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15											15
C _I	Input Capacitance		Any Input					5	7.5				pF	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.* T_{High} = + 125°C for HCC device + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions			Value			Unit	
		R_x (k Ω)	C_x (pF)	V_{DD} (V)	Min.	Typ.	Max.		
t_{PLH}, t_{PHL}	Trigger Propagation Delay Time (+ TR, - TR to Q, \bar{Q})	5 to 10.000	≥ 15	5		250	500	ns	
				10		125	250		
				15		100	200		
t_{WH}, t_{WL}	Trigger Pulse Width	5 to 10.000	≥ 15	5	140	70		ns	
				10	60	30			
				15	40	20			
t_{TLH}	Transition Time	5 to 10.000	≥ 15	5		100	200		
				10		50	100		
				15		40	80		
t_{THL}	Transition Time	5 to 10.000	15 to 10.000	5		100	200	ns	
				10		50	100		
				15		40	80		
		5 to 10.000	0.01 μF to 0.1 μF	5		150	300		
				10		75	150		
				15		65	130		
		5 to 10.000	0.1 μF to 1 μF	5		250	500		
				10		150	300		
				15		80	160		
t_{PLH}, t_{PHL}	Propagation Delay Time (reset)	5 to 10.000	≥ 15	5		225	450	ns	
				10		125	250		
				15		75	150		
t_{wR}	Pulse Width (reset)	100	15	5	200	100		ns	
				10	80	40			
				15	60	30			
			1000	5	1200	600			
				10	600	300			
				15	500	250			
		0.1 μF	5	50	250		μs		
			10	30	15				
			15	20	10				
t_r, t_f (TR)	Rise or Fall Time (trigger)		5 to 15				100	μs	
	Pulse Width Match Between Circuits in Same Package	10	10.000			5	5	10	%
						10	7.5	15	
						15	7.5	15	

Figure 2 : Typical Output Low (sink) Current Characteristics.

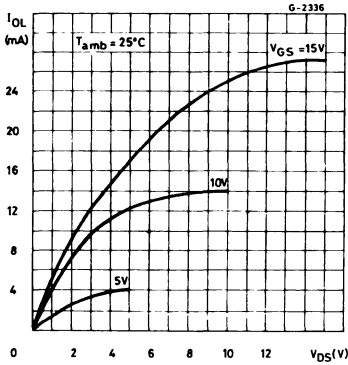


Figure 3 : Minimum Output Low (sink) Current Characteristics.

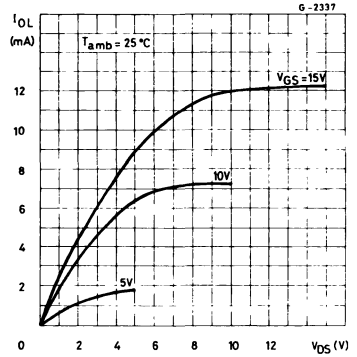


Figure 4 : Typical Output High (source) Current Characteristics.

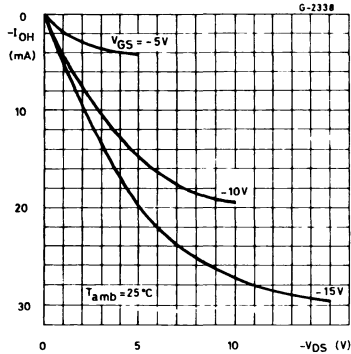


Figure 5 : Minimum Output High (source) Current Characteristics.

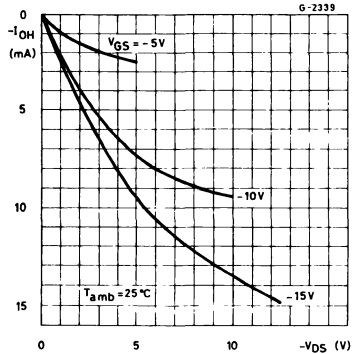


Figure 6 : Typical Propagation Delay Times vs. Load Capacitance, Trigger in to Q out. (All values of C_X and R_X).

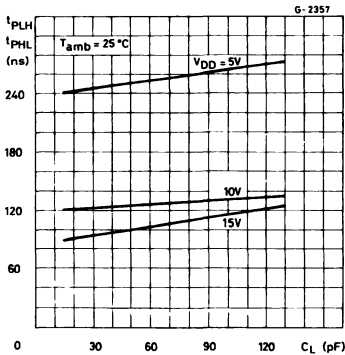


Figure 7 : Transition Time vs. Load Capacitance for $R_X = 5k\Omega$, $10000 k\Omega$ and $C_X = 15pF$, $10000pF$.

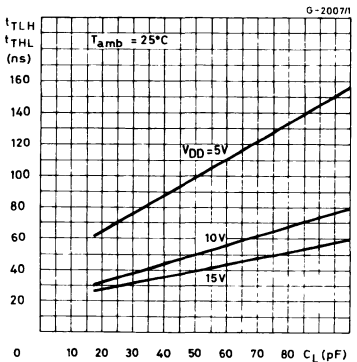


Figure 8 : Typical External Resistance vs. Pulse Width at Various V_{DD} and C_X .

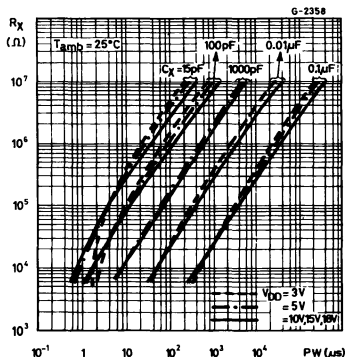


Figure 9 : Typical External Capacitance vs. Pulse Width at Various V_{DD} and R_X .

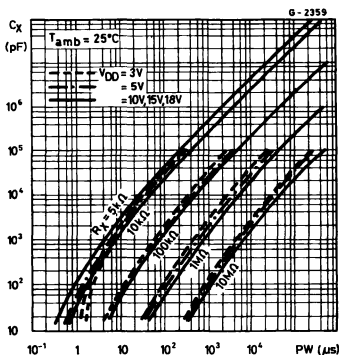


Figure 10 : Typical Minimum Reset Pulse Width vs. External Capacitance.

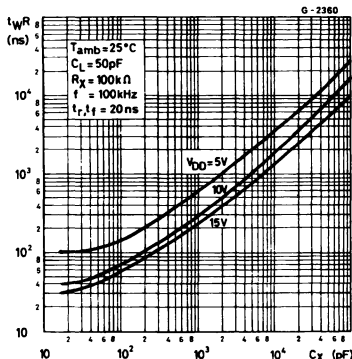
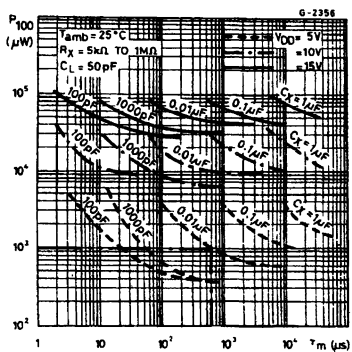


Figure 11 : Average Power Dissipation for 100% Duty Cycle vs. One-shot Pulse width.



To calculate average power dissipation (P) for less than 100% duty cycle :
 P_{100} = average power for 100% duty cycle

$$P = \left(\frac{\tau_m}{\tau_T} \right) P_{100}$$

where τ_m = one-shot pulse width
 τ_T = trigger pulse period

e.g. : For $\tau_m \dots 600ms$ $t_T = 1000ms$,
 $C_X = 0.01\mu F$, $V_{DD} = 5V$

$$P = \left(\frac{600}{1000} \right) 103\mu W = 600\mu W$$

(see dotted line on graph)

The diagram shows a square wave pulse with a width τ_m and a period τ_T . The pulse is high for τ_m and low for $\tau_T - \tau_m$.

TEST CIRCUITS

Figure 12 : Quiescent -Device Current.

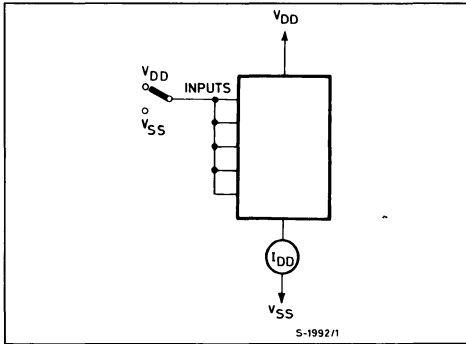


Figure 13 : Input-Voltage.

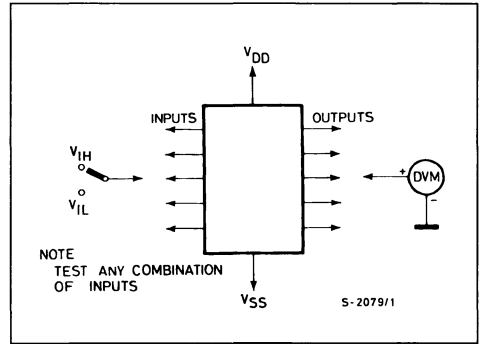
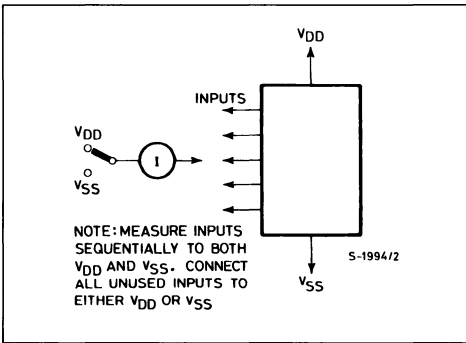


Figure 14 : Input Leakage.



TYPICAL APPLICATIONS

Figure 15 : Astable Multivibrator with Restart after Reset Capability.

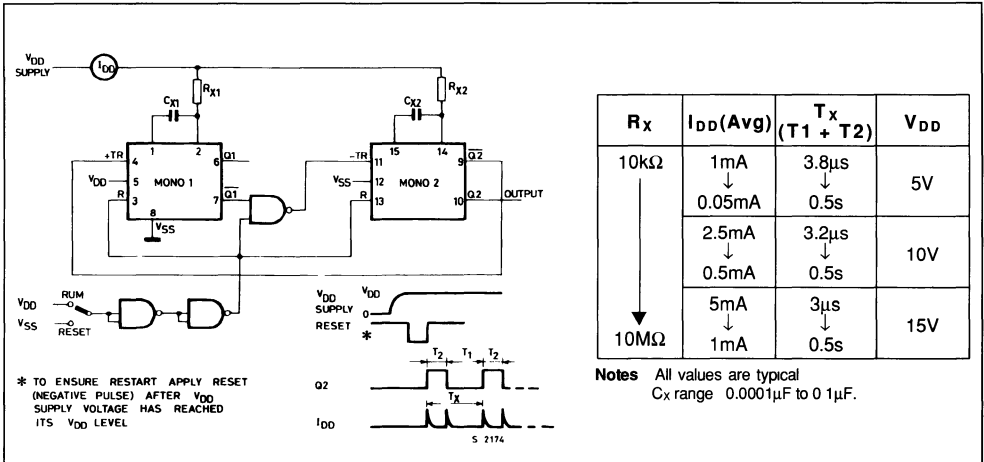
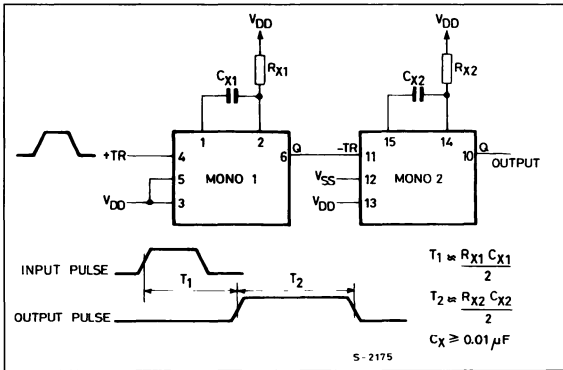
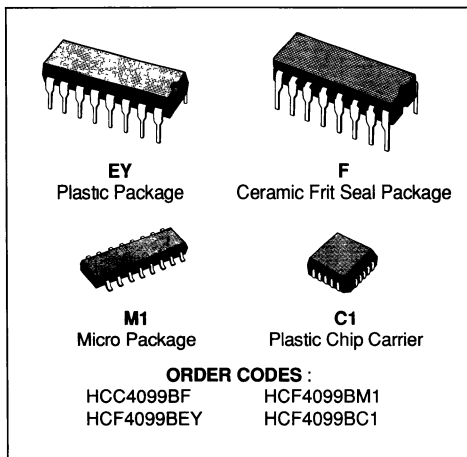


Figure 16 : Pulse Delay.

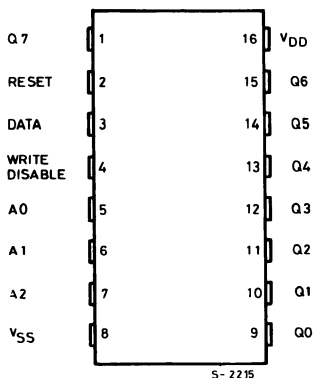


8-BIT ADDRESSABLE LATCH

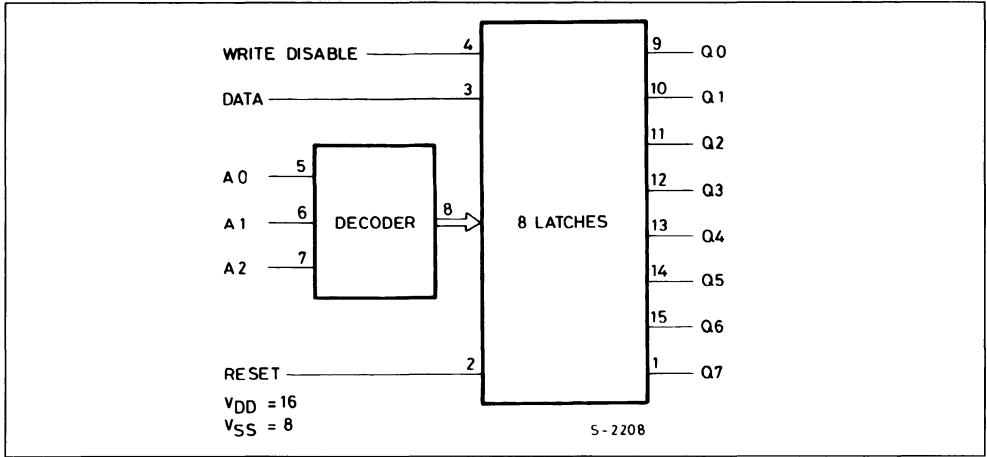
- SERIAL DATA INPUT - ACTIVE PARALLEL OUTPUT
- STORAGE REGISTER CAPABILITY - MASTER CLEAR
- CAN FUNCTION AS DEMULTIPLEXER
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

The **HCC4099B** (extended temperature range) and **HCF4099B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The HCC/HCF4099B 8-bit addressable latch is a serial-input, parallel-output storage register that can perform a variety of functions. Data are inputted to a particular bit in the latch when that bit is addressed (by means of inputs A0, A1, A2) and when WRITE DISABLE is at a low level. When WRITE DISABLE is high, data entry is inhibited ; however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs. A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer ; the bit that is addressed has an active output which follows the data input, while all unaddressed bits are held to a logic "0" level.

PIN CONNECTIONS


FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{Tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

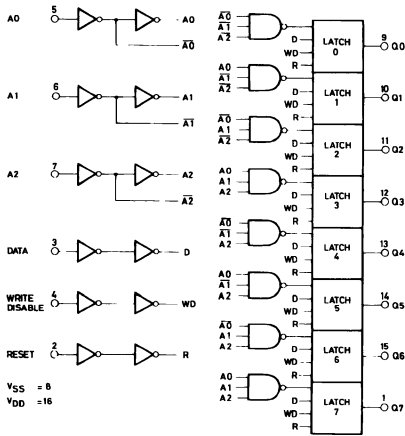
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

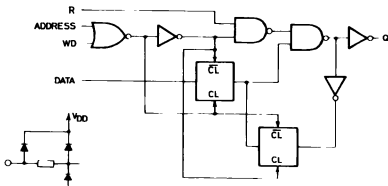
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM

1 of 8 latches



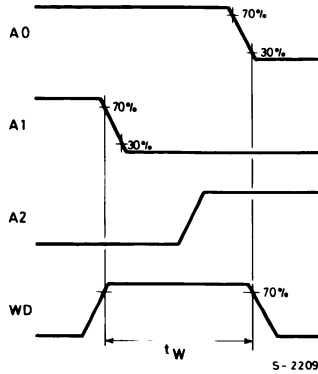
YSS = 8
YDD = 16



ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

S-2211

Definition of WRITE DISABLE ON Time



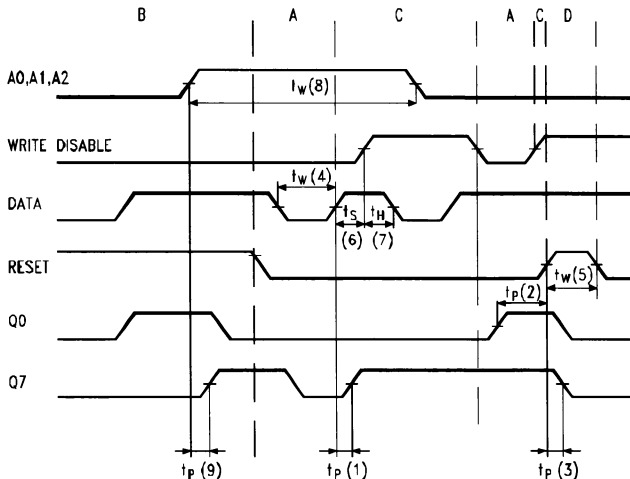
S-2209

Types	Mode Selection			
	WD	R		
A	0	0	Follows Data	Holds Previous State
B	0	1	Follows Data	Reset to "0" (active high 8-channel demultiplexer)
C	1	0	Holds Previous State	
D	1	1	Reset to "0"	Reset to "0"

WD = WRITE DISABLE

R = RESET

Master Timing Diagram



SC05140

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
	HCF Types	0/ 5			5		20		0.04	20		150		
		0/10			10		40		0.04	40		300		
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18	± 0.1		±10 ⁻⁵	± 0.1		± 1	μA	
		HCF Types	0/15											15
C _I	Input Capacitance		Any Input						5	7.5			pF	

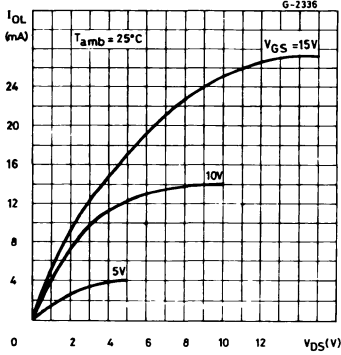
* T_{Low} = - 55°C for HCC device - 40°C for HCF device
 * T_{High} = + 125°C for HCC device + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V,

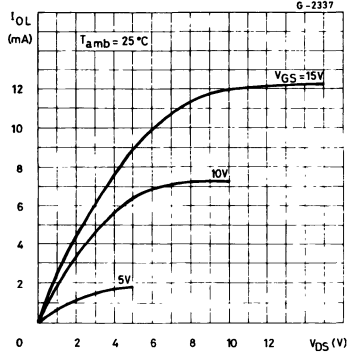
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter		Test Conditions (see master timing diagram)	Value			Unit	
				V_{DD} (V)	Min.	Typ.		Max.
t_{PLH} , t_{PHL}	Propagation Delay Time	Data to Output	(1)	5		200	400	ns
				10		75	150	
				15		50	100	
		Write Disable to Output	(2)	5		200	400	
				10		80	160	
				15		60	120	
	Address to Output	(9)	5		225	450		
			10		100	200		
			15		75	150		
t_{PHL}	Propagation Delay Time	Reset to Output	(3)	5		175	350	
				10		80	160	
				15		65	130	
t_{THL} , t_{TLH}	Transition Time	Any Output		5		100	200	ns
				10		50	100	
				15		40	80	
t_w	Pulse Width	Data	(4)	5	200	100		ns
				10	100	50		
				15	80	40		
		Address	(8)	5	400	200		
				10	200	100		
				15	125	65		
		Reset	(5)	5	150	75		
				10	75	40		
				15	50	25		
t_{setup}	Setup Time	Data to Write Disable	(6)	5	100	50		ns
				10	50	25		
				15	35	20		
t_{hold}	Hold Time	Data to Write Disable	(7)	5	150	75		ns
				10	75	40		
				15	50	25		

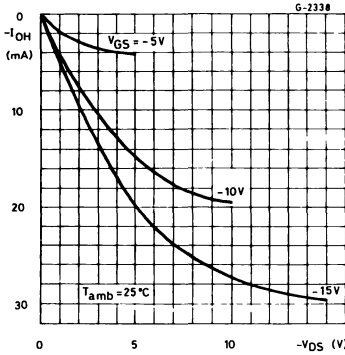
Typical Output Low (sink) Current Characteristics.



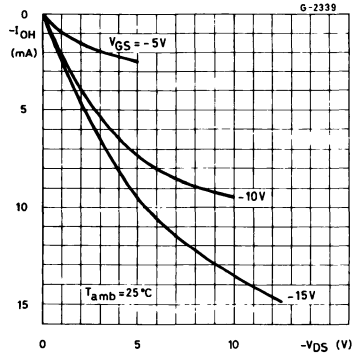
Minimum Output Low (sink) Current Characteristics.



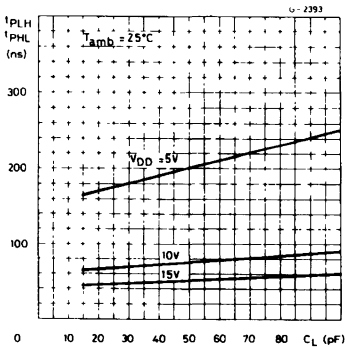
Typical Output High (source) Current Characteristics.



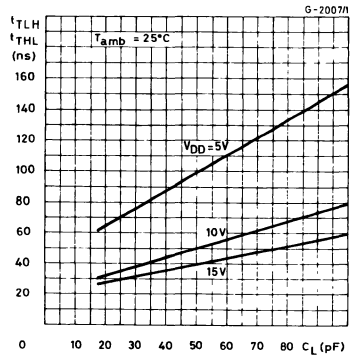
Minimum Output High (source) Current Characteristics.



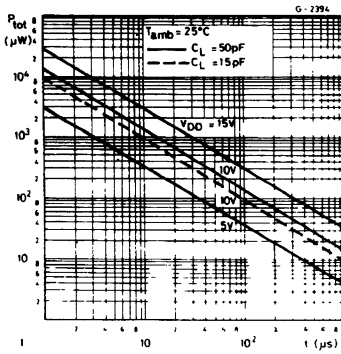
Typical Propagation Delay Time (data to Qn) vs. Load Capacitance.



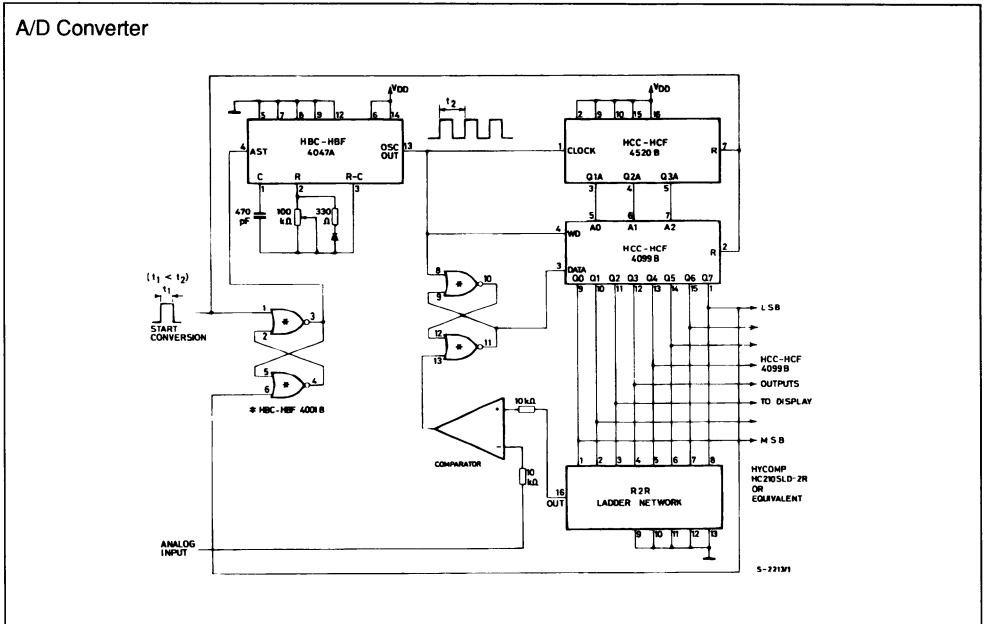
Typical Transition Time vs. Load Capacitance.



Typical Dynamic power Dissipation vs. Address Cycle Time.

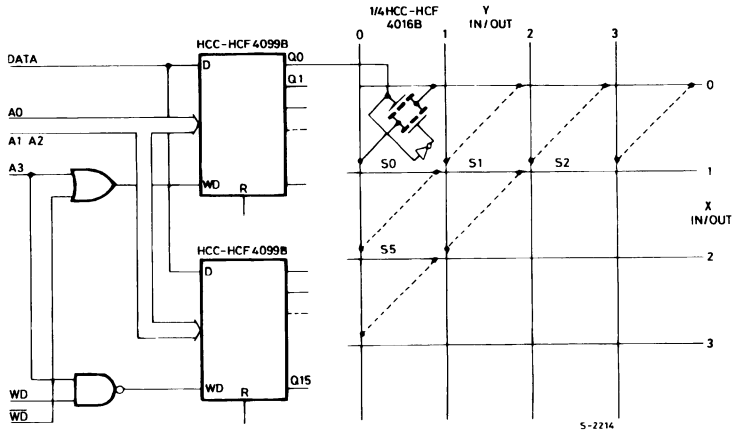


TYPICAL APPLICATIONS

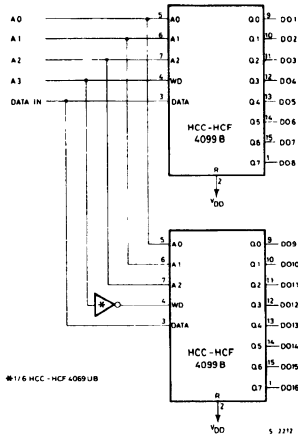


TYPICAL APPLICATIONS

Multiple Selection Decoding – 4x4 Crosspoint Switch

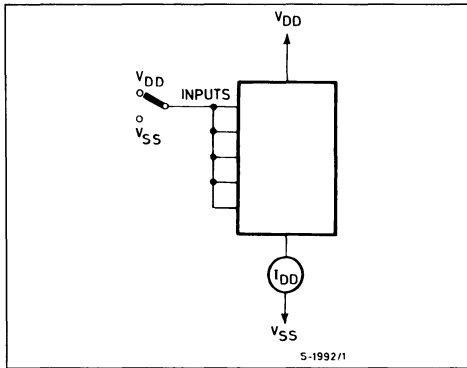


1 of 16 Decoder/demultiplexer

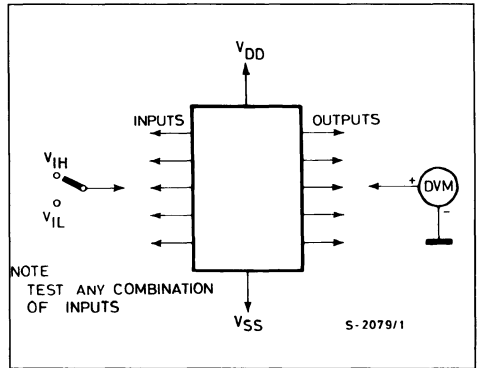


TEST CIRCUITS

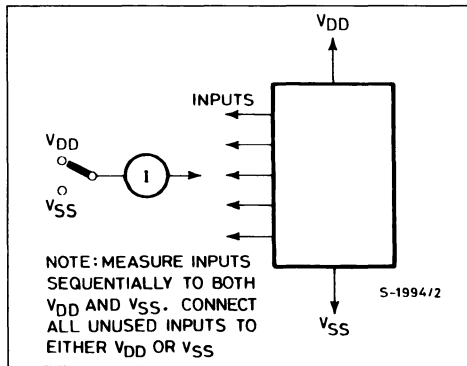
Quiescent Device Current.



Input Voltage.

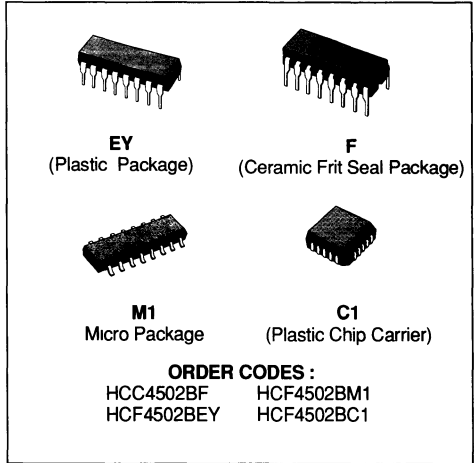


Input Current.

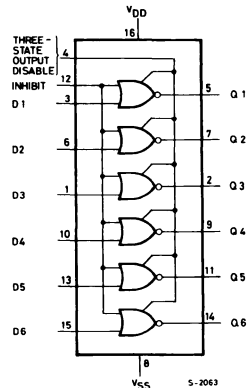


STROBED HEX INVERTER/BUFFER

- 2 TTL-LOAD OUTPUT DRIVE CAPABILITY
- 3-STATE OUTPUTS
- COMMON OUTPUT-DISABLE CONTROL
- INHIBIT CONTROL
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

The **HCC4502B** (extended temperature range) and **HCF4502B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF 4502B** consists of six inverter-buffers with 3-state outputs. A logic "1" on the OUTPUT DISABLE input produces a high-impedance state in all six outputs. This feature permits common busing of the outputs, thus simplifying system design. A logic "1" on the INHIBIT input switches all six outputs to logic "0" if the OUTPUT DISABLE input is a logic "0". This device is capable of driving two standard TTL loads, which is equivalent to six times the JEDEC "B" series I_{OL} standard.

PIN CONNECTIONS


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to + 18	V
	HCF Types	3 to + 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

TRUTH TABLE

Disable	Inhibit	Dn	Qn
0	0	0	1
0	0	1	0
0	1	X	0
1	X	X	Z

X = don't care
 Z = high impedance
 Logic 1 = high
 Logic 0 = low

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95				4.95		V	
		0/10	< 1	10	9.95		9.95				9.95			
		0/15	< 1	15	14.95		14.95				14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05		V	
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		-1.15	mA	
			0/ 5	4.6		5	-0.64		-0.51	- 1		-0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	-1.53		-1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	-0.52		-0.44	- 1		-0.36		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	3.84		3.06	6		2.10	mA	
			0/10	0.5		10	9.6		7.8	15.6		5.4		
			0/15	1.5		15	25.2		20.4	40.8		14.4		
		HCF Types	0/ 5	0.4		5	3.11		2.6	6		2.10		
			0/10	0.5		10	7.05		6.63	15.6		5.61		
			0/15	1.5		15	20.4		17.3	40.8		14.2		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18	\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15											15
I _{OH} , I _{OL}	3-state Output	HCC Types	0/18			18	\pm 0.4		\pm 10 ⁻⁴	\pm 0.4		\pm 12	μ A	
		HCF Types	0/15			15	\pm 1.0		\pm 10 ⁻⁴	\pm 1.0		\pm 7.5		
C _I	Input Capacitance		Any Input						5	7.5		pF		

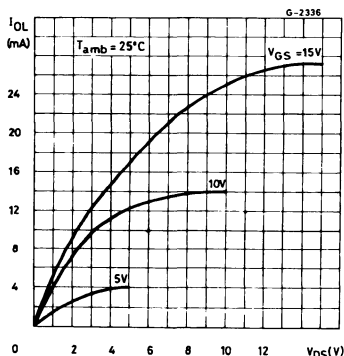
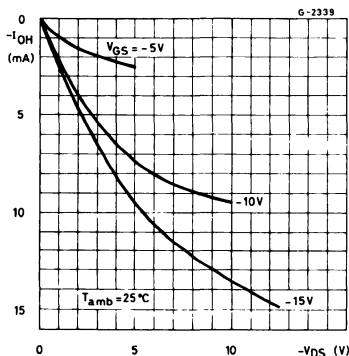
* T_{Low}= - 55°C for HCC device - 40°C for HCF device* T_{High}= + 125°C for HCC device + 85°C for HCF deviceThe Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$
 typical temperature coefficient for all V_{DD} values is $0.3\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

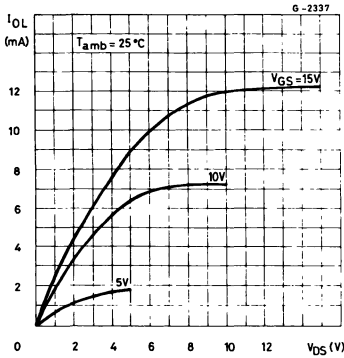
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Data or Inhibit Delay Time		5		135	270	ns
			10		60	120	
			15		40	80	
t_{PLH}	Data or Inhibit Delay Time		5		190	380	ns
			10		90	180	
			15		65	30	
t_{PHZ}	Disable Delay Time (output high to high impedance)		5		60	120	ns
			10		40	80	
			15		30	60	
t_{PZH}	Disable Delay Time (high impedance to output high)		5		110	220	ns
			10		50	100	
			15		40	80	
t_{PLZ}	Disable Delay Time (output low to high impedance)		5		125	250	ns
			10		65	130	
			15		55	110	
t_{PZL}	Disable Delay Time (high impedance to output low)		5		125	250	ns
			10		55	110	
			15		40	80	
t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{THL}	Transition Time		5		60	120	ns
			10		30	60	
			15		20	40	

Minimum Output High (source) Current Characteristics.

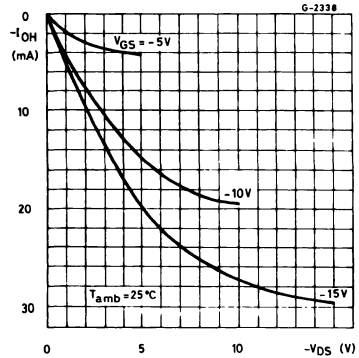
Typical Output Low (sink) Current.



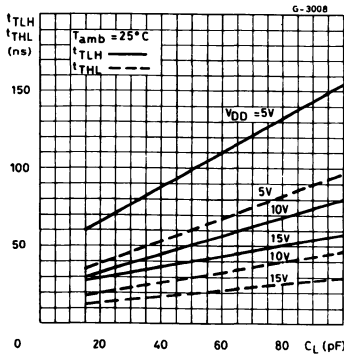
Minimum Output Low (sink) Current Characteristics.



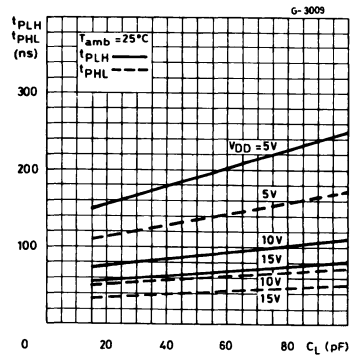
Typical Output High (source) Current Characteristics.



Typical Transition Time vs. Load Capacitance.

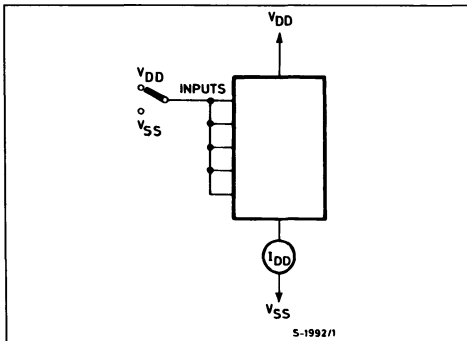


Typical Propagation Delay Time vs. Load Capacitance.

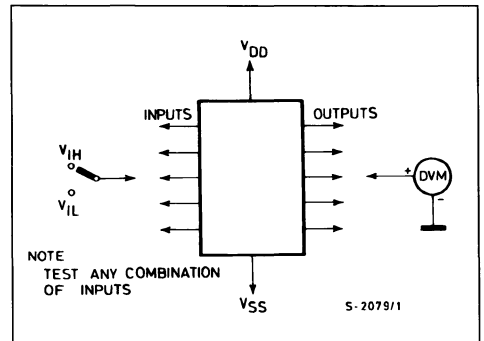


TEST CIRCUIT

Quiescent Device Current.

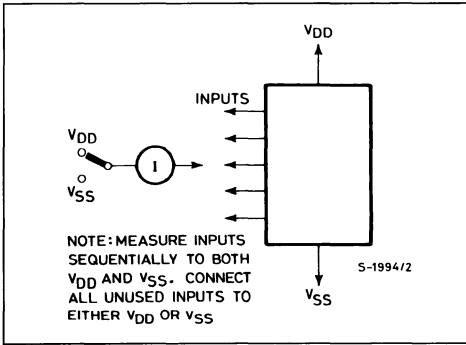


Input Voltage.



TEST CIRCUIT (continued)

Input Leakage Current.



TEST CIRCUIT AND WAVEFORMS

Disable Delay Time.

S-2064

S-2065

Test Conditions		
Test	Pin 15	Point A
t_{PHZ}	V_{SS}	V_{SS}
t_{PLZ}	V_{DD}	V_{DD}
t_{PZL}	V_{DD}	V_{DD}
t_{PZH}	V_{SS}	V_{SS}



HEX BUFFER

- 1 TTL-LOAD OUTPUT DRIVE CAPABILITY
- 2 OUTPUT-DISABLE CONTROLS
- 3 STATE OUTPUTS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N⁰. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

EY
(Plastic Package)

F
(Ceramic Package)

M1
(Micro Package)

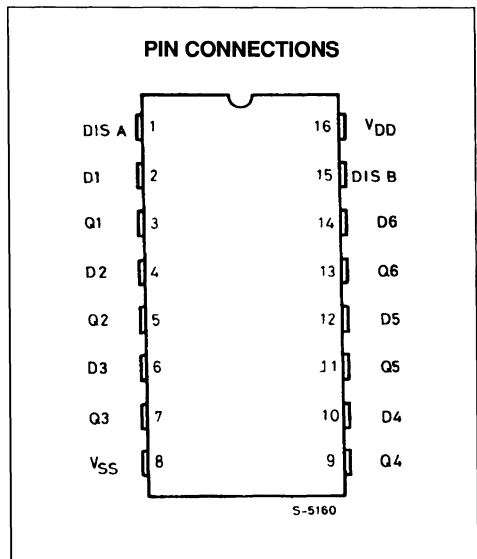
C1
(Chip Carrier)

ORDER CODES :
HCC4503BF HCF4503BM1
HCF4503BEY HCF4503BC1

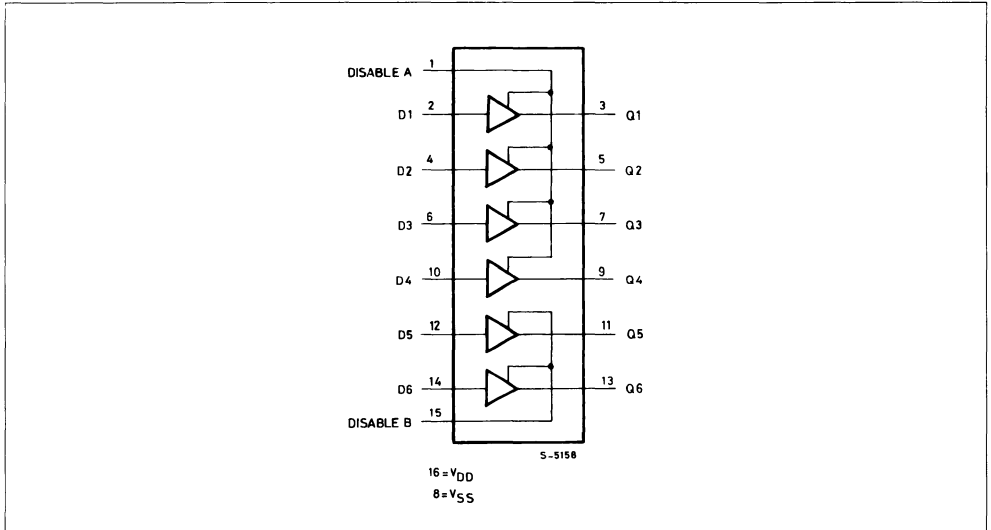
DESCRIPTION

The **HCC4503B** (extended temperature range) and **HCF4503B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package, and plastic micro package.

The **HCC/HCF4503B** is a hex noninverting buffer with 3-state outputs having high sink and source-current capability. Two disable controls are provided, one of which controls four buffers and the other controls the remaining two buffers.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package Temperature Range	200 100	mW mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C
T _{stg}	Storage Temperature	-65 to +150	°C

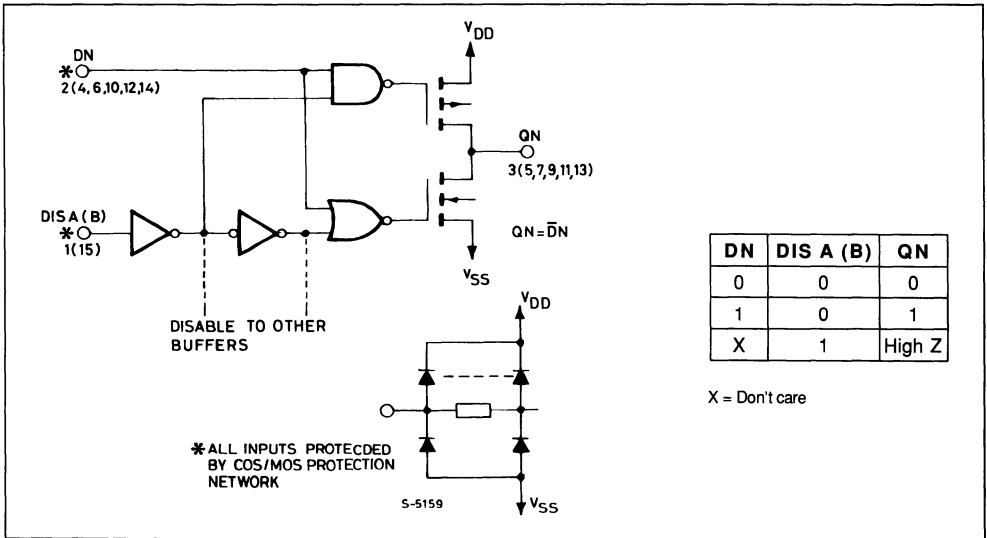
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C

LOGIC DIAGRAM AND TRUTH TABLE



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
V _{OH}	Output High Voltage		0/5	< 1	5	4.95		4.95			4.95			V
			0/10	< 1	10	9.95		9.95			9.95			
			0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage		5/0	< 1	5		0.05			0.05		0.05	V	
			10/0	< 1	10		0.05			0.05		0.05		
			15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5	5	-5.8		-4.8	-6.1		-3		mA	
			0/5	4.6	5	-1.2		-1.02	-1.9		-0.7			
			0/10	9.5	10	-3.1		-2.6	-3.7		-1.8			
			0/15	13.5	15	-8.2		-6.8	-14.1		-4.8			
		HCF Types	0/5	2.5	5	-4.8		-4.1	-5.2		-2.9			
			0/5	4.6	5	-1		-0.8	-1.6		-0.6			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4	5	2.6		2.1	2.3		1.3		mA	
			0/10	0.5	10	6.5		5.5	2.6		3.8			
			0/15	1.5	15	19.2		16.1	2.3		11.2			
I _{OH}	Input Leakage Current	HCF Types	0/5	0.4	5	2.1		1.8	1.9		1.2		μ A	
			0/10	0.5	10	5.4		4.7	5.3		3.3			
			0/15	1.5	15	16		13.7	19.5		9.7			
I _{IH} , I _{IL}	Input Leakage Current		0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
			0/15		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1		
I _{OH}	Input Leakage Current		0/18	Any Input	18		± 0.4		$\pm 10^{-4}$	± 0.4		± 12	μ A	
			0/15		15		± 1.0		$\pm 10^{-4}$	± 1.0		± 7.5		
C _I	Input Capacitance		Any Input					5	7.5			pF		

* T_{LOW} = -55 °C for HCC device -40 °C for HCF device

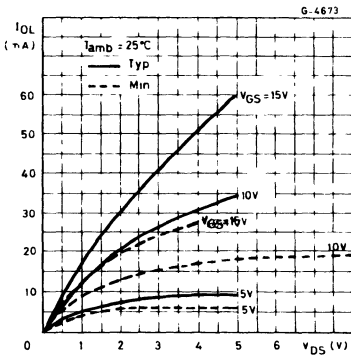
* T_{HIGH} = +125 °C for HCC device +85 °C for HCF device

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

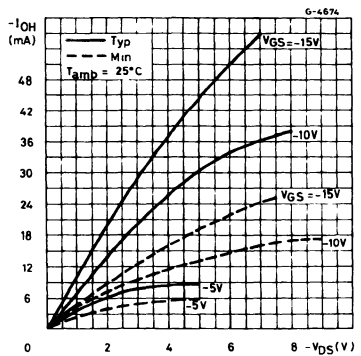
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\%/^{\circ}C$, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PLH}	Propagation Delay Time	5		75	150	ns	
		10		35	70		
		15		25	50		
t_{PHL}	Propagation Delay Time	5		55	110	ns	
		10		25	50		
		15		17	35		
t_{PHZ} t_{PZH}	3-State Propagation Delay Time	5		70	140	ns	
		10		30	60		
		15		25	50		
t_{PZL} t_{PLZ}	3-State Propagation Delay Time	5		90	180	ns	
		10		40	80		
		15		35	70		
t_{TLH}	Transition Time	5		50	90	ns	
		10		30	45		
		15		25	35		
t_{THL}	Transition Time	5		35	70	ns	
		10		20	40		
		15		13	25		

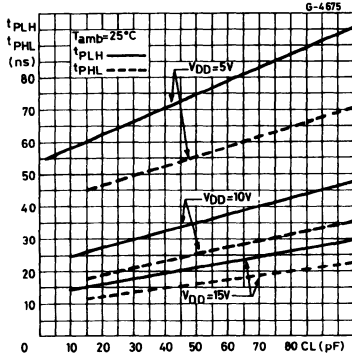
N-Channel Output Low (sink) Current Characteristics.



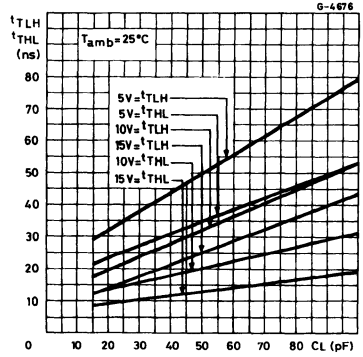
P-Channel Output High (source) Current Characteristics.



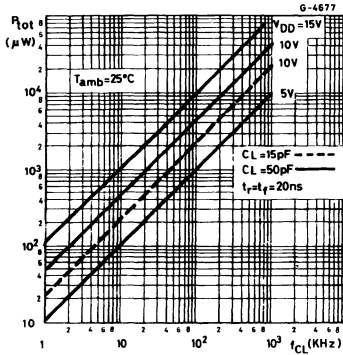
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

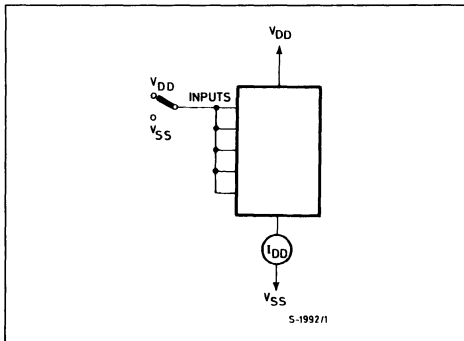


Typical Dynamic Power Dissipation vs. Frequency.

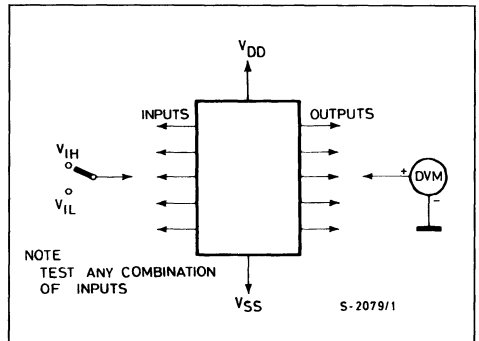


TEST CIRCUITS

Quiescent Device Current.

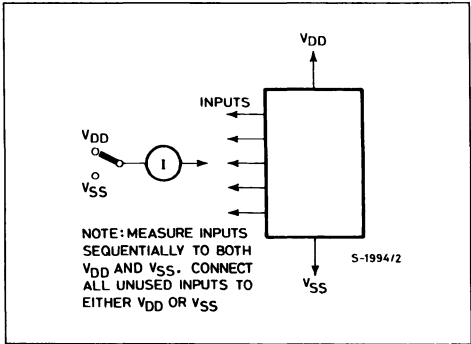


Input Voltage.

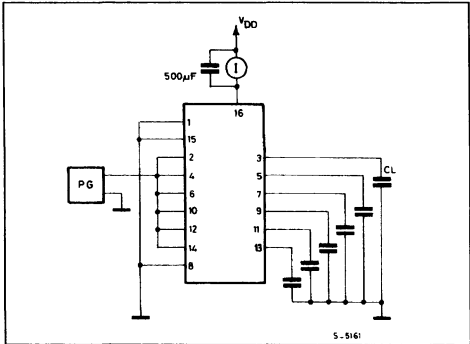


TEST CIRCUIT (continued)

Input Leakage Current.



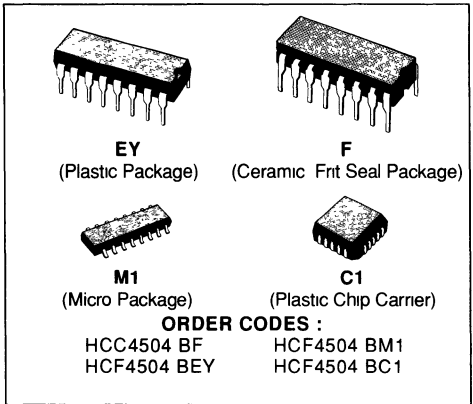
Dynamic Power Dissipation.



HEX TTL OR CMOS TO CMOS LEVEL SHIFTER

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SUPPLY VOLTAGE RANGE 3V TO 18V FOR V_{DD} AND V_{CC}
- UP TRANSLATES FROM A LOW TO A HIGH VOLTAGE OR DOWN TRANSLATES FROM A HIGH TO A LOW VOLTAGE
- INPUT THRESHOLD CAN BE SHIFTED FOR TTL COMPATIBILITY



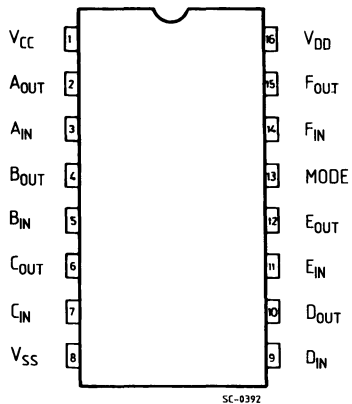
DESCRIPTION

The HCC4504B and HCF4504B are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages or in 16-pin SO micro-packages.

The HCC4504B and HCF4504B are hex non-inverting level shifters. They will shift a TTL signal to CMOS logic levels for any CMOS supply voltage between 5V and 15V. A control input also allows interface from CMOS to CMOS at one logic level to another logic level. Either up or down level translating is accomplished by selection of power supply levels V_{DD} and V_{CC} . The V_{CC} level sets the input signal levels ; V_{DD} selects the output voltage levels.

The supply current is typically 1nA at $V_{DD} = 10V$ for CMOS to CMOS operation. For TTL to CMOS translation the supply current is typically 2.5mA taken from V_{CC} .

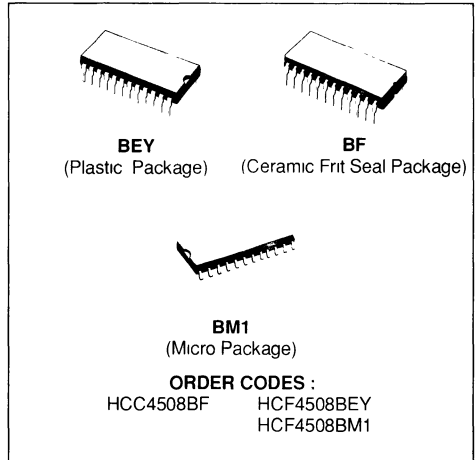
PIN CONNECTION (top view)





DUAL 4-BIT LATCH

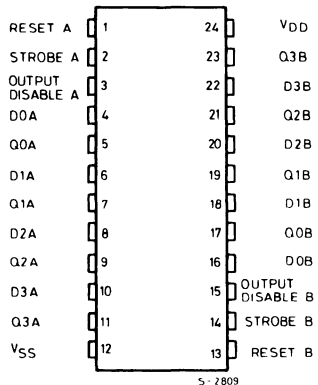
- TWO INDEPENDENT 4-BIT LATCHES
- INDIVIDUAL MASTER RESET FOR EACH 4-BIT-LATCH
- 3-STATE OUTPUTS WITH HIGH-IMPEDANCE STATE FOR BUS LINE APPLICATION
- MEDIUM-SPEED OPERATION $t_{PHL} = t_{PLH} = 70ns$ (TYP.) AT $V_{DD} = 10V$ AND $C_L = 50pF$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N⁰ 13A. "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



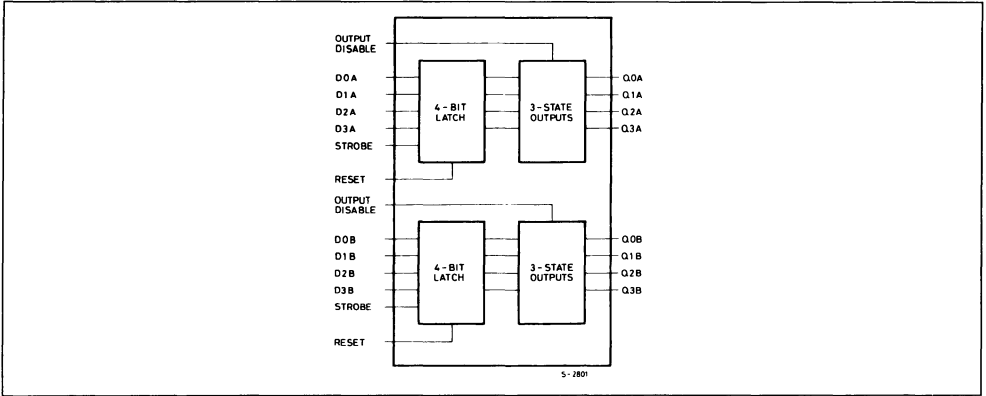
DESCRIPTION

The **HCC4508B** (extended temperature range) and the **HCF4508B** (intermediate temperature range) are monolithic integrated circuits available in 24-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4508B** dual 4-bit latch contains two identical 4-bit latches with separate STROBE, RESET, and OUTPUT DISABLE controls. With the STROBE line in the high state, the data on the "D" inputs appear at the corresponding "Q" outputs provided the DISABLE line is in the low state. Changing the STROBE line to the low state locks the data into the latch. A high on the reset line forces the outputs to a low level regardless of the state of the STROBE input. The outputs are forced to the high-impedance state for bus line applications by a high level on the DISABLE input

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings "may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

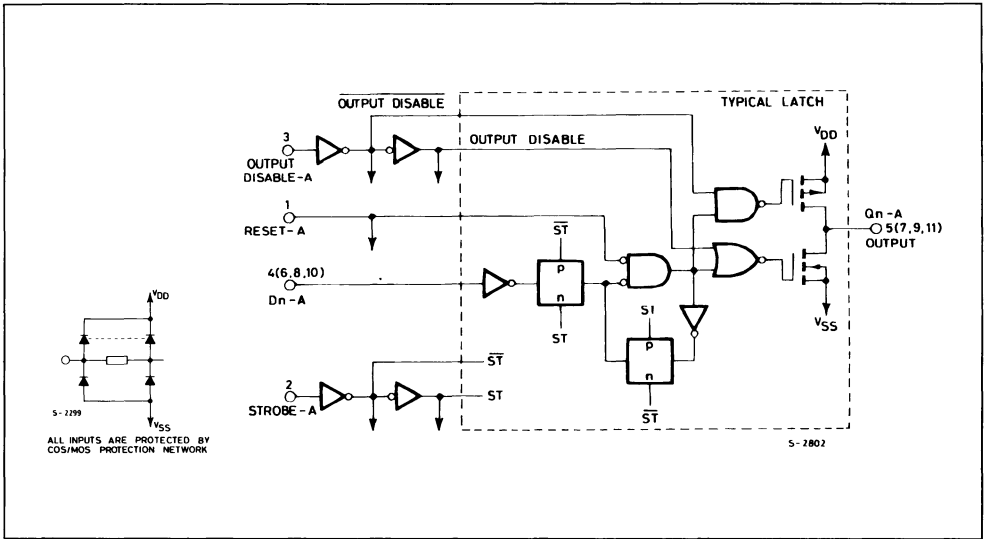
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to + 18	V
		3 to + 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM (A section)

1 OF 4 IDENTICAL LATCHES WITH COMMON OUTPUT DISABLE, RESET AND STROBE



TRUTH TABLE

Reset	Disab.	Strobe	D Input	Q Input
0	0	1	1	1
0	0	1	0	0
0	0	0	X	Latched
1	0	X	X	0
X	1	X	X	Z

1 = High level
0 = Low level

X = Don't care
Z = High impedance

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5	150	μA	
			0/10			10		10		0.04	10	300		
			0/15			15		20		0.04	20	600		
		0/20			20		100		0.08	100	3000			
		HCF Types	0/5			5		20		0.04	20	150		
			0/10			10		40		0.04	40	300		
0/15				15		80		0.04	80	600				
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95	V		
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05	0.05	V		
		10/0		< 1	10		0.05			0.05	0.05			
		15/0		< 1	15		0.05			0.05	0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5	1.5	V		
			9/1	< 1	10		3			3	3			
			13.5/1.5	< 1	15		4			4	4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
		0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
0/10	9.5			10	-1.3		-1.1	-2.6		-0.9				
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		±10 ⁻⁵	± 0.1		± 1	μA
		HCF Types	0/15			15		± 0.3		±10 ⁻⁵	± 0.3		± 1	
I _O	3-state Output	HCC Types	0/18			18		± 0.4		±10 ⁻⁴	± 0.4		± 12	μA
		HCF Types	0/15			15		± 1.0		±10 ⁻⁴	± 1.0		± 7.5	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low} = -55°C for HCC device -40°C for HCF device

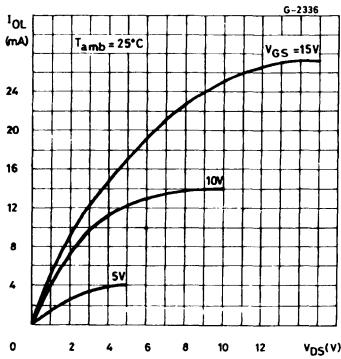
* T_{High} = +125°C for HCC device +85°C for HCF device

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V

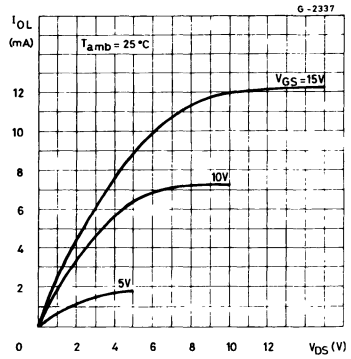
DYNAMIC ELECTRICAL CHARACTERISTICS(T_{amb} = 25°C, input t_r, t_f = 20ns, C_L = 50pF, R_L = 200kΩ, unless otherwise specified)

Symbol	Parameter		Test Conditions	Value			Unit
			V _{DD} (V)	Min	Typ.	Max.	
t _{THL} , t _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t _{W(R)}	Reset Pulse Width		5	200	100		ns
			10	140	70		
			15	100	50		
t _{W(st)}	Strobe Pulse Width		5	140	70		ns
			10	80	40		
			15	70	35		
t _{setup}	Setup Time		5	50	25		ns
			10	30	15		
			15	20	10		
t _H	Hold Time		5	0	0		ns
			10	0	0		
			15	0	0		
t _{PHL} , t _{PLH}	Propagation Delay Time:	Strobe to Data Out	5		130	260	ns
			10		70	140	
			15		50	100	
		Data in to Data Out	5		105	210	ns
			10		60	120	
			15		45	90	
		Reset to Data Out	5		90	180	ns
			10		50	100	
			15		40	80	
t _{PHZ}	3-State Propagation Delay Time: Output High to High impedance		5		90	180	ns
			10		50	100	
			15		35	70	
t _{PZH}	High Impedance to Output High		5		90	180	ns
			10		50	100	
			15		35	70	
t _{PLZ}	Output Low to High Impedance		5		90	180	ns
			10		50	100	
			15		35	70	
t _{PZL}	High Impedance to Output Low		5		90	180	ns
			10		50	100	
			15		35	70	

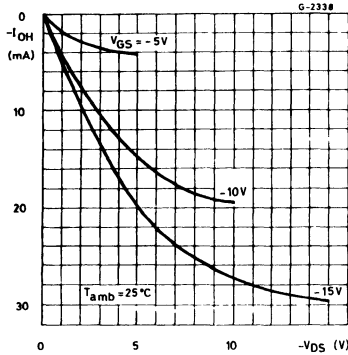
Typical Output Low (sink) Current Characteristics.



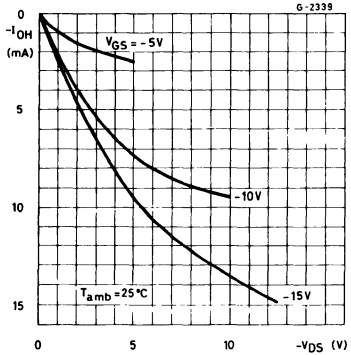
Minimum Output Low (sink) Current Characteristics.



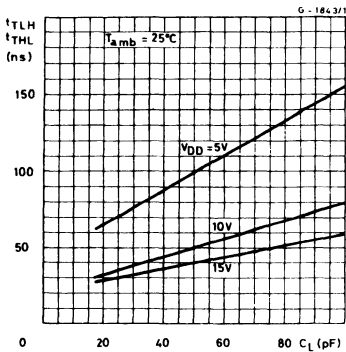
Typical Output High (source) Current Characteristics.



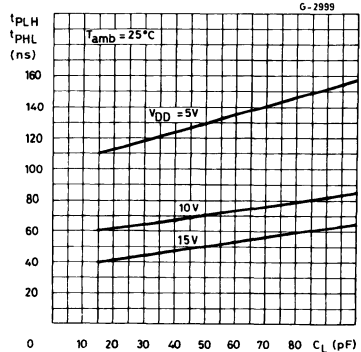
Minimum Output High (source) Current Characteristics.



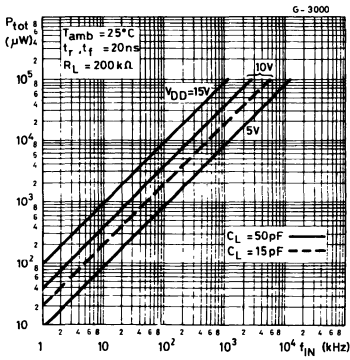
Typical Transition Time vs. Load Capacitance.



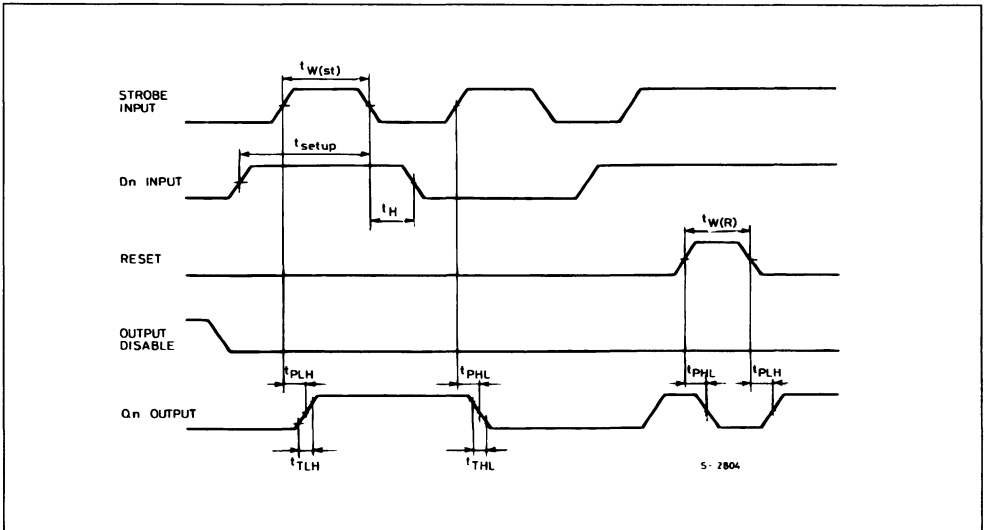
Typical Propagation Delay Time vs. Load Capacitance (strobe to dataout).



Typical Power Dissipation vs. Frequency .

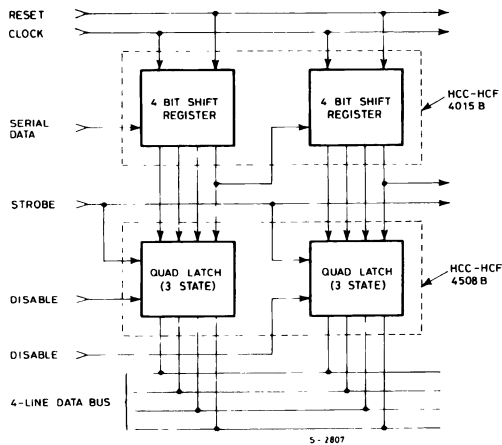


TEST WAVEFORM

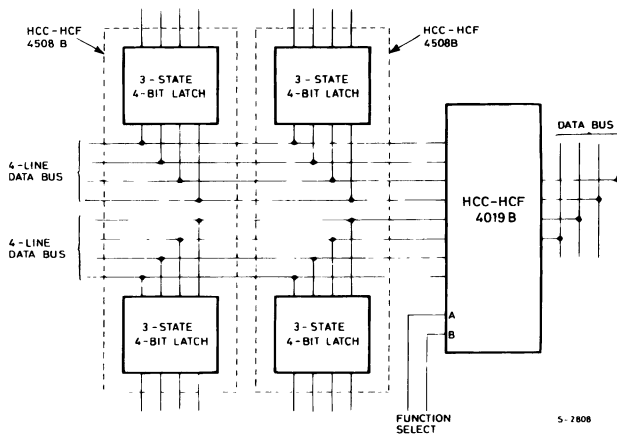


TYPICAL APPLICATIONS

A) Figure 15 : Bus register.



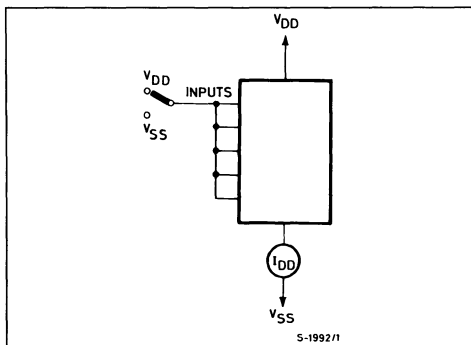
B) Figure 16 : Dual multiplexed bus register with function select.



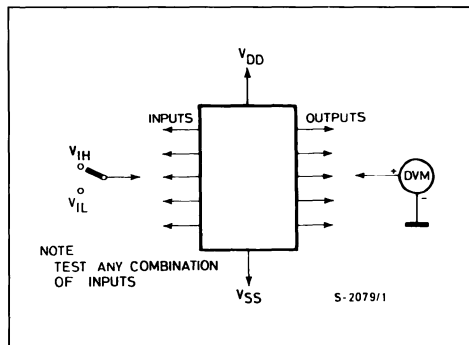
A	B	Function
0	0	Inhibit (all 0)
1	0	Select A Bus
0	1	Select B Bus
1	1	$A_1 + B_1$

TEST CIRCUITS

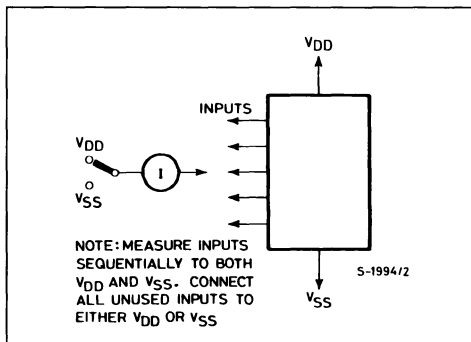
Quiescent Device Current Test Circuit.



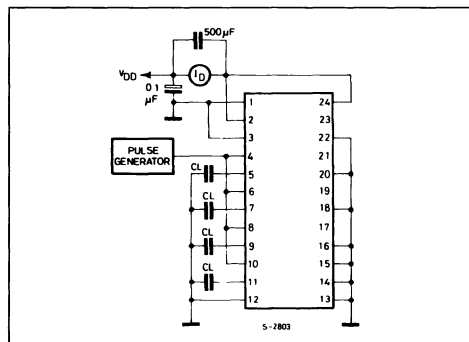
Input Voltage Test Circuit.



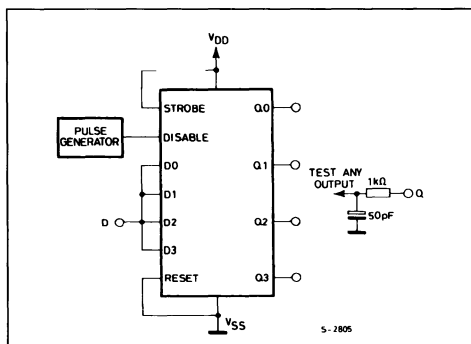
Input Current Test Circuit.



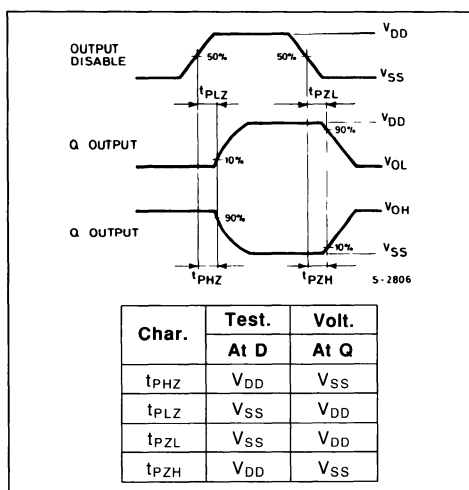
Power Dissipation Test Circuit.



Output Disable.



Waveform.

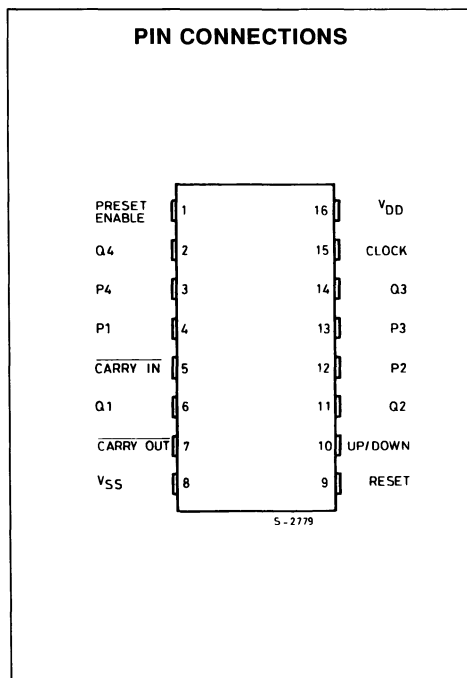
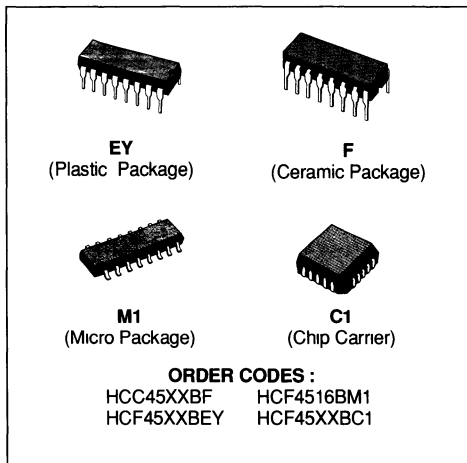


PRESETTABLE UP/DOWN COUNTERS

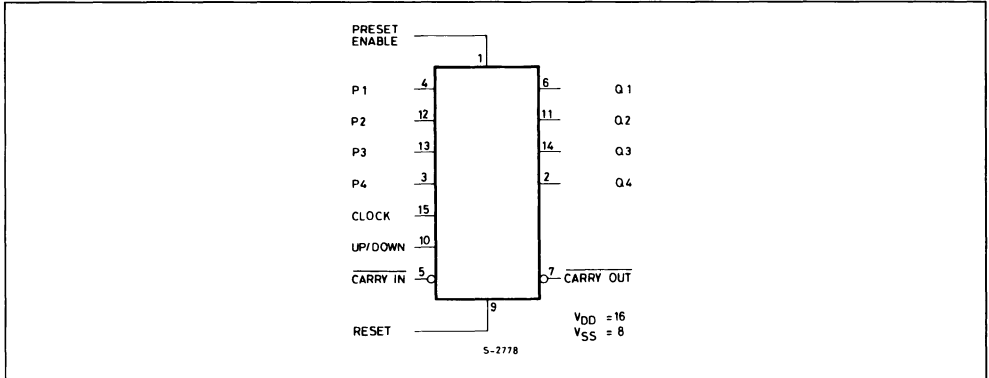
- MEDIUM SPEED OPERATION $f_{CL} = 8\text{MHz TYP. AT } 10\text{V}$
- SYNCHRONOUS INTERNAL CARRY PROPAGATION
- RESET AND PRESET CAPABILITY
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4510B**, **HCC4516B** (extended temperature range) and the **HCF4510B**, **HCF4516B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4510B** Presettable BCD Up/Down Counter and the **HCC/HCF4516B** Presettable Binary Up/Down Counter consist of four synchronously clocked D-type flip-flops (with a gating structure to provide T-type flip-flop capability) connected as counters. These counters can be cleared by a high level on the RESET line, and can be preset to any binary number present on the jam inputs by a high level on the PRESET ENABLE line. The **HCC/HCF4510B** will count out of non-BCD counter states in a maximum of two clock pulses in the up mode, and a maximum of four clock pulses in the down mode. If the CARRY-IN input is held low, the counter advances up or down on each positive-going clock transition. Synchronous cascading is accomplished by connecting all clock inputs in parallel and connecting the CARRY-OUT of a less significant stage to the CARRY-IN of a more significant stage. The **HCC/HCF4510B** and **HCC/HCF4516B** can be cascaded in the ripple mode by connecting the CARRY-OUT to the clock of the next stage. If the UP/DOWN input changes during a terminal count, the CARRY-OUT must be gated with the clock, and the UP/DOWN input must change while the clock is high. This method provides a clean clock signal to the subsequent counting stage.



FUNCTIONAL DIAGRAM



CL	\overline{CI}	U/D	PE	R	Action
X	1	X	0	0	No Count
$\overline{\text{L}}$	0	1	0	0	Count Up
$\overline{\text{L}}$	0	0	0	0	Count Down
X	X	X	1	0	Preset
X	X	X	X	1	Reset

X = Don't care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operationale sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

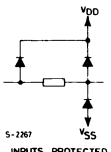
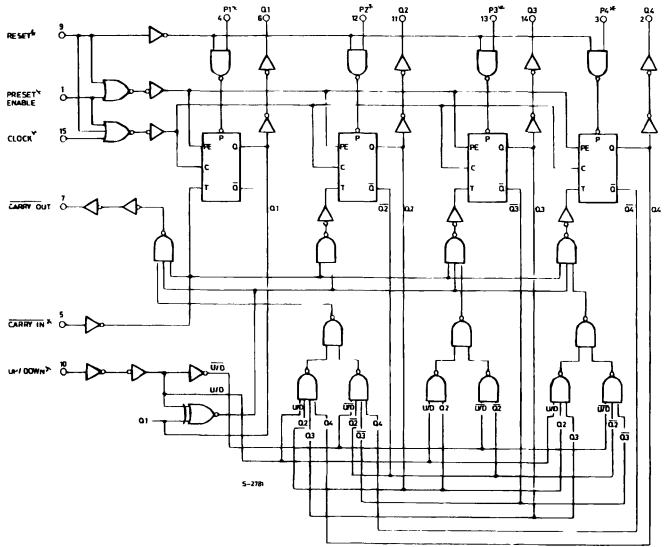
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to + 18 3 to + 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$

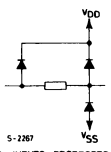
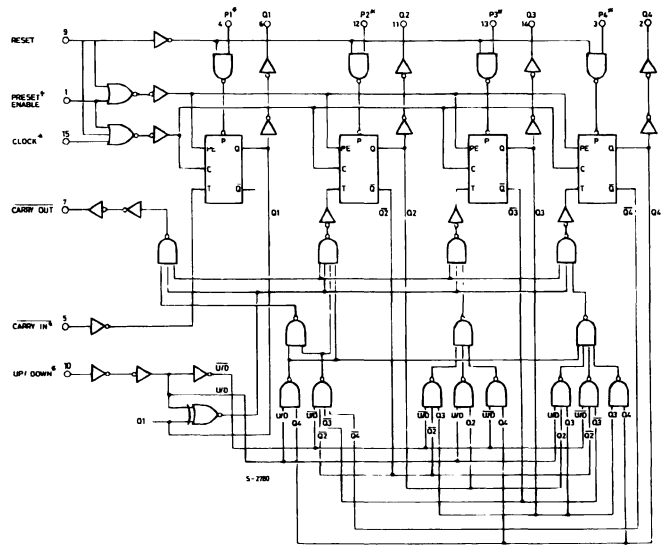
LOGIC DIAGRAMS

4510B



ALL INPUTS PROTECTED BY COS/MOS PROTECTION NETWORK

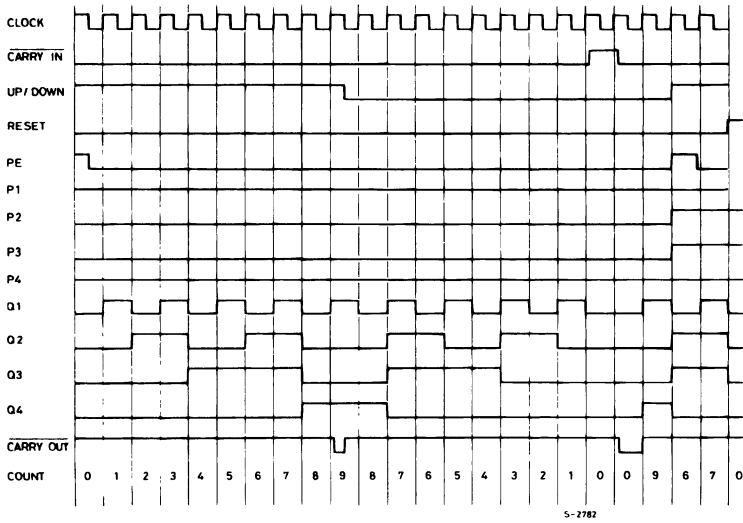
4516B



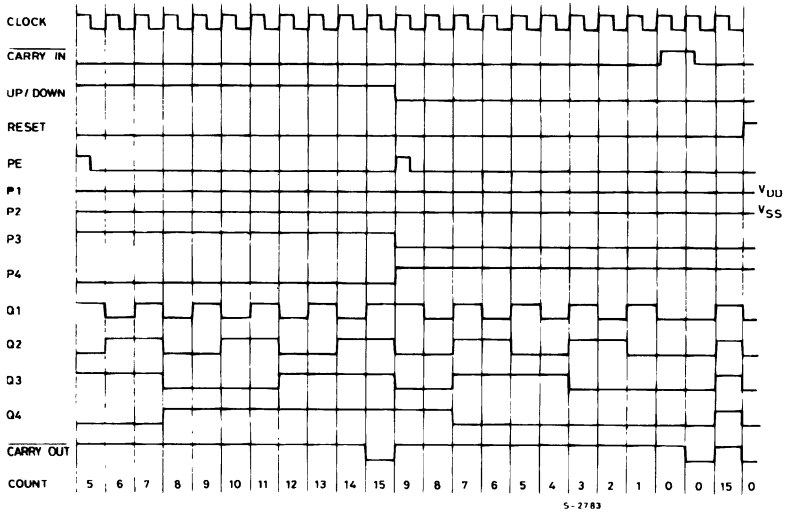
ALL INPUTS PROTECTED BY COS/MOS PROTECTION NETWORK

TIMING DIAGRAMS

4510B



4516B



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

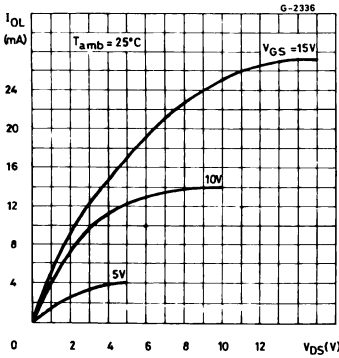
* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_L = 50pF$, $R_L = 200k\Omega$
 typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}C$, all input rise and fall times = 20ns)

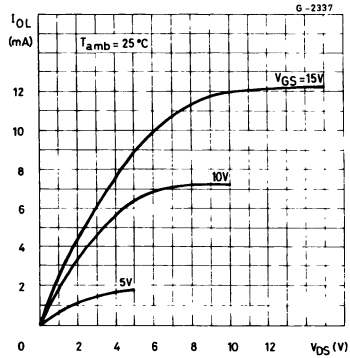
Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)	Min.	Typ.	Max.		
t_{PHL}, t_{PLH}	Propagation Delay Time Clock to Q Output	5		200	400	ns	
		10		100	200		
		15		75	150		
t_{PHL}, t_{PLH}	Propagation Delay Time Preset or Reset to Q Output	5		210	420	ns	
		10		105	210		
		15		80	160		
t_{PHL}, t_{PLH}	Propagation Delay Time Clock to Carry Out	5		240	480	ns	
		10		120	240		
		15		90	180		
t_{PHL}, t_{PLH}	Propagation Delay Time Carry in to Carry Out	5		125	250	ns	
		10		60	120		
		15		50	100		
t_{PHL}, t_{PLH}	Propagation Delay Time Preset or Reset to Carry Out	5		320	640	ns	
		10		160	320		
		15		125	250		
t_{THL}, t_{TLH}	Transition Time	5		100	200	ns	
		10		50	100		
		15		40	80		
f_{max}	Max. Clock Frequency	5	2	4		MHz	
		10	4	8			
		15	5.5	11			
t_w	Clock Pulse Width	5	150			ns	
		10	75				
		15	60				
	•Preset Enable or Reset Removal Time	5	150			ns	
		10	80				
		15	60				
t_r, t_f	*Clock Rise and Fall Time	5			15	μs	
		10			5		
		15			5		
t_{setup}	Carry in Setup Time	5	130			ns	
		10	60				
		15	45				
t_{setup}	Up-down Setup Time	5	360			ns	
		10	160				
		15	110				
t_w	Preset Enable or Reset Pulse Width	5	220			ns	
		10	100				
		15	75				

- Time required after the falling edge of the reset or preset enable inputs before the rising edge of the clock will trigger the counter (similar to setup time)
- * If more than unit is cascaded in the parallel clocked application, t_{CL} should be made less than or equal to the sum of the fixed propagation delay at 15pF and the transition time of the carry output driving stage for the estimated capacitive load

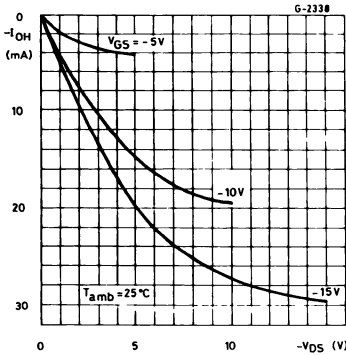
Typical Output Low (sink) Current Characteristics.



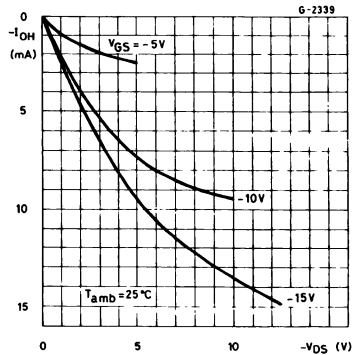
Minimum Output Low (sink) Current Characteristics.



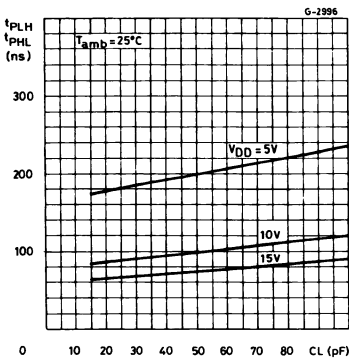
Typical Output High (source) Current Characteristics.



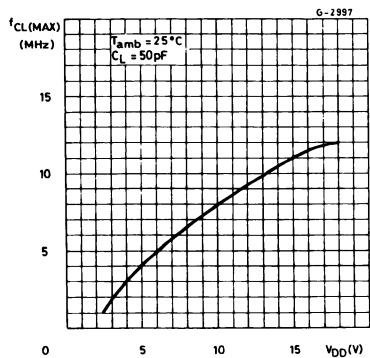
Minimum Output High (source) Current Characteristics.



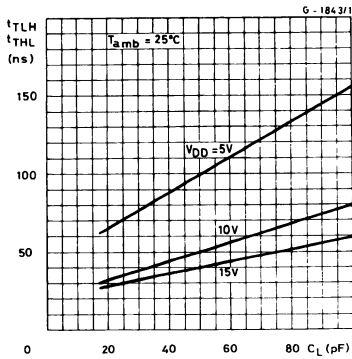
Typical Propagation Delay Time vs. Load Capacitance for Clock to Q Output.



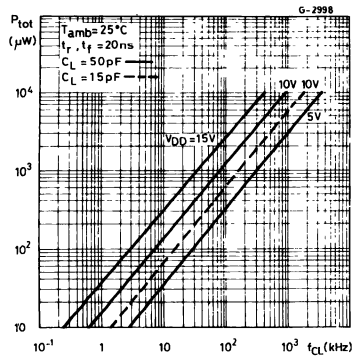
Typical Maximum Clock Input Frequency vs. Supply Voltage.



Typical Transition Time vs. Load Capacitance.

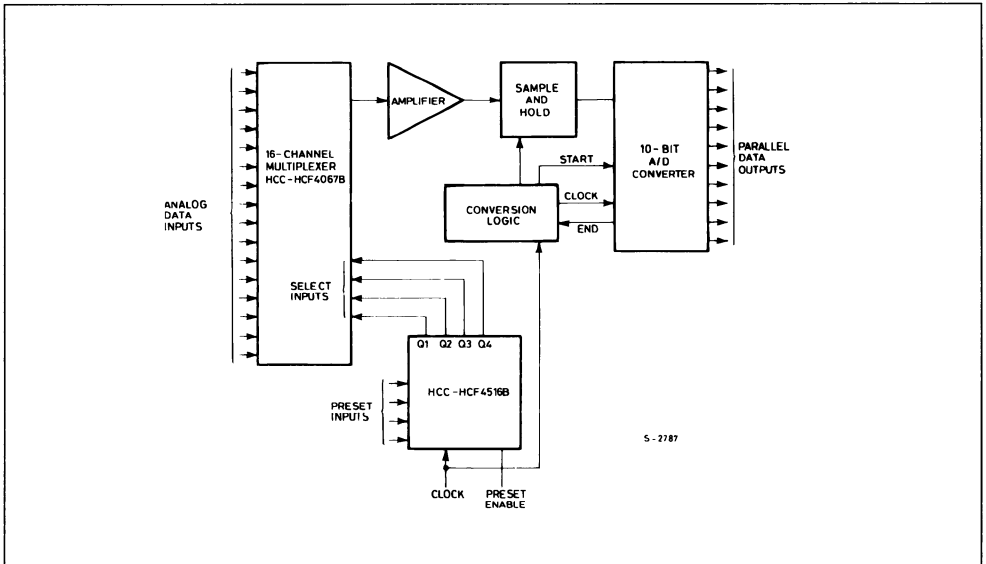


Typical Dynamic Power Dissipation vs. Frequency.



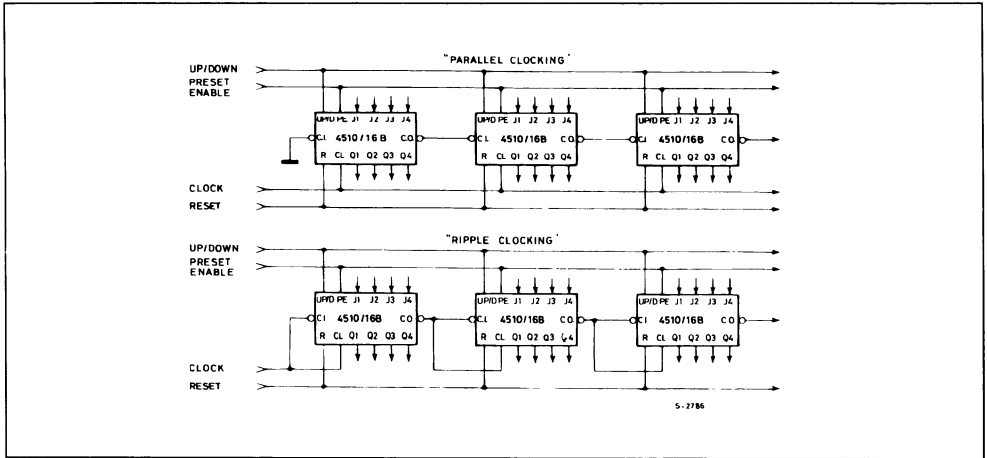
TYPICAL APPLICATIONS

TYPICAL 16-CHANNEL, 10 BIT DATA ACQUISITION SYSTEM



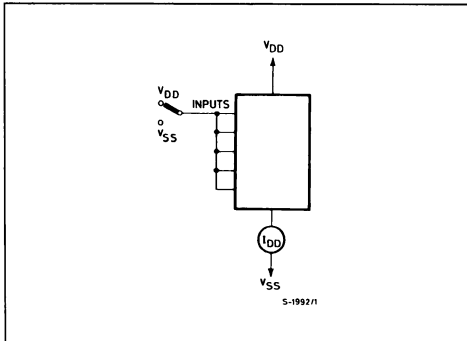
This acquisition system can be operated in the random access mode by jamming in the channel number at the present inputs, or in the sequential mode by clocking the HCC/HCF4516B

CASCADING COUNTER PACKAGES

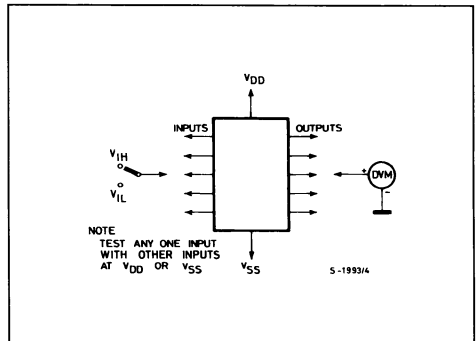


TEST CIRCUITS

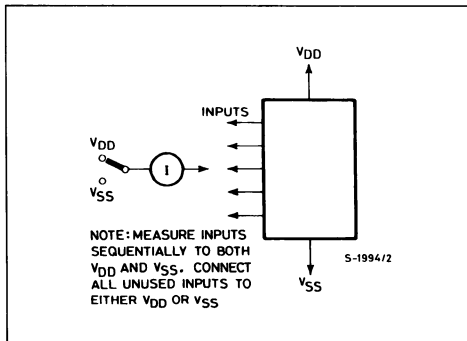
Quiescent Device Current.



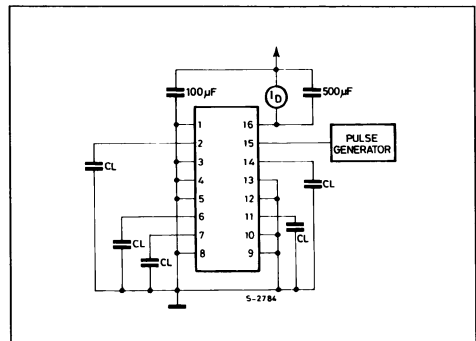
Noise Immunity.



Input Leakage Current.

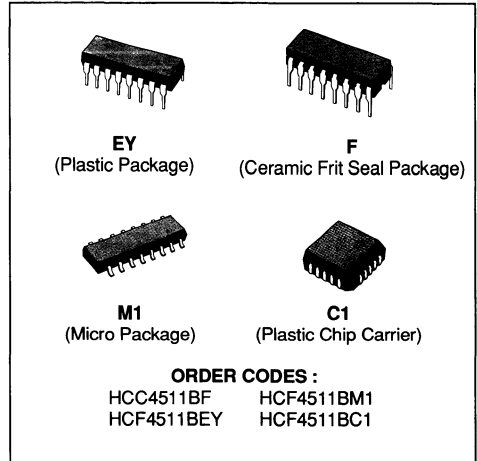


Power Dissipation and Input Waveform.



BCD-TO-SEVEN SEGMENT LATCH/DECODER/DRIVER

- HIGH-OUTPUT-SOURCING CAPABILITY (up to 25 mA)
- INPUT LATCHES FOR BCD CODE STORAGE
- LAMP TEST AND BLANKING CAPABILITY
- 7-SEGMENT OUTPUTS BLANKED FOR BCD INPUT CODES > 1001
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100mA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



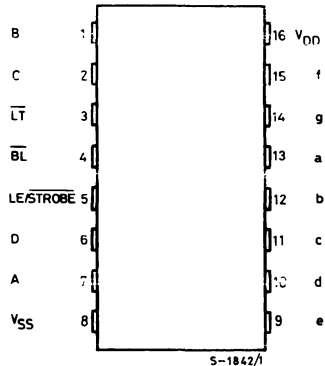
DESCRIPTION

The **HCC 4511B** (extended temperature range) and the **HCF 4511B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

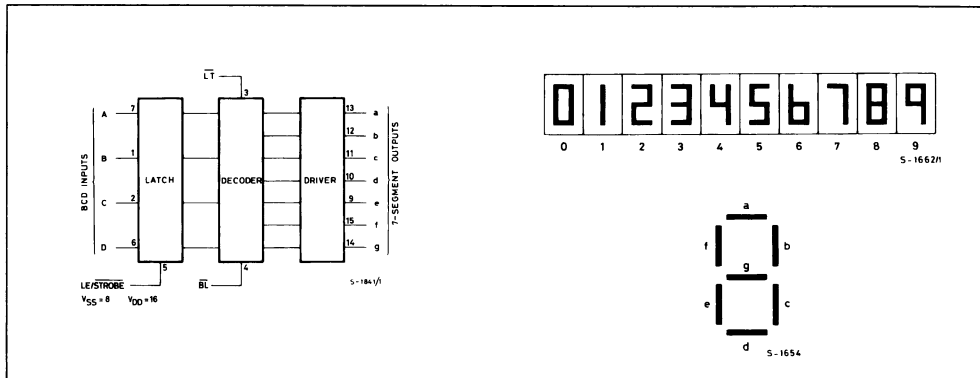
The **HCC/HCF 4511B** types are BCD-to-7-segment latch decoder drivers constructed with COS/MOS logic and n-p-n bipolar transistor output devices on a single monolithic structure. These devices combine the low quiescent power dissipation and high noise immunity features of COS/MOS with n-p-n bipolar output transistors capable of sourcing up to 25 mA. This capability allows the **HCC/HCF 4511B** types to drive LED's and other displays directly.

Lamp Test (\overline{LT}), Blanking (\overline{BL}), and Latch Enable or Strobe inputs are provided to test the display, shut off or intensity-modulate it, and store or strobe a BCD code, respectively. Several different signal may be multiplexed and displayed when external multiplexing circuitry is used.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

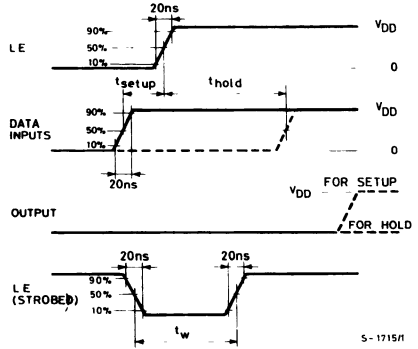
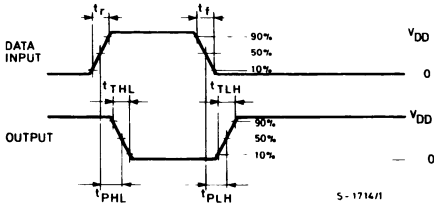
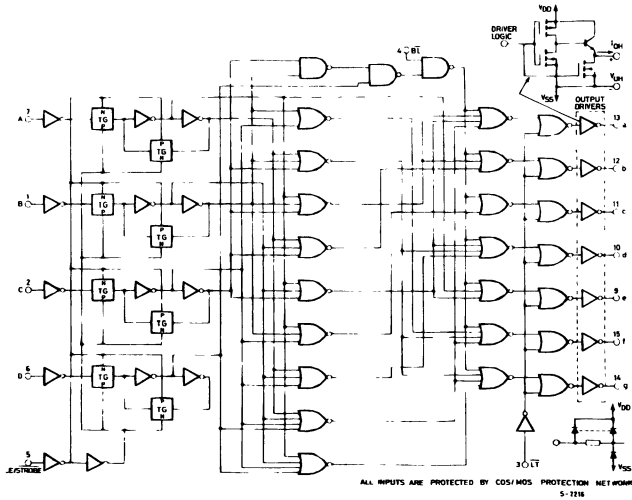
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS



TRUTH TABLE

LE	\overline{BI}	\overline{LT}	D	C	B	A	a	b	c	d	e	f	g	Display
X	X	0	X	X	X	X	1	1	1	1	1	1	1	8
X	0	1	X	X	X	X	0	0	0	0	0	0	0	Blank
0	1	1	0	0	0	0	1	1	1	1	1	1	0	0
0	1	1	0	0	0	1	0	1	1	0	0	0	0	1
0	1	1	0	0	1	0	1	1	0	1	1	0	1	2
0	1	1	0	0	1	1	1	1	1	1	0	0	1	3
0	1	1	0	1	0	0	0	1	1	0	0	1	1	4
0	1	1	0	1	0	1	1	0	1	1	0	1	1	5
0	1	1	0	1	1	0	0	0	1	1	1	1	1	6
0	1	1	0	1	1	1	1	1	1	0	0	0	0	7
0	1	1	1	0	0	0	1	1	1	1	1	1	1	8
0	1	1	1	0	0	1	1	1	1	0	0	1	1	9
0	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	0	1	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	1	0	0	0	0	0	0	0	Blank
1	1	1	X	X	X	X				*				*

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit																
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *																	
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.															
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A															
			0/10			10		10		0.04	10		300																
			0/15			15		20		0.04	20		600																
			0/20			20		100		0.08	100		3000																
		HCF Types	0/5			5		20		0.04	20		150																
			0/10			10		40		0.04	40		300																
			0/15			15		80		0.04	80		600																
V _{OH}	Output High Voltage	0/5			5	4		4.1	4.55		4.2		V																
		0/10			10	9		9.1	9.55		9.2																		
		0/15			15	14		14.1	14.55		14.2																		
V _{OL}	Output Low Voltage	5/0			5		0.05			0.05		0.05	V																
		10/0			10		0.05			0.05		0.05																	
		15/0			15		0.05			0.05		0.05																	
V _{IH}	Input High Voltage		0.5/3.8		5	3.5		3.5			3.5		V																
			1/8.8		10	7		7			7																		
			1.5/13.8		15	11		11			11																		
V _{IL}	Input Low Voltage		3.8/0.5		5		1.5			1.5		1.5	V																
			8.8/1		10		3			3		3																	
			13.8/1.5		15		4			4		4																	
V _{OH}	Output Drive Voltage	HCC Types		0	5	4.1	4.10	4.55	4.20					V															
				5												3.80	3.90	4.10	3.90										
				10																	3.55	3.40	3.75						
				15																					3.40	3.10	3.55		
				20																									9
				25	10	8.85	9	9.15	9.25						V														
				0													8.70	8.60	8.90	8.40									
				5																		8.60	8.30	8.75					
				10																						14	14.10	14.55	14.20
				15																									
				20	15	13.90	14	14.20	14						V														
				25													13.75	13.70	13.95	13.50									
				0																		13.65	13.50	13.80	13.10				
				5																									

* T_{Low} = -55°C for HCC device, -40°C for HCF device.* T_{High} = +125°C for HCC device; +85°C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
V _{OH}	Output Drive Voltage	HCF Types			0	5	4.1	4.1	4.57		4.1		V	
					5					4.24				
					10		3.6	3.6	4.12		3.3			
					15				3.94					
					20		2.8	2.8	3.75		2.5			
					25				3.54					
					0	10	9.1	9.1	9.58		9.1		V	
					5				9.26					
					10		8.75	8.75	9.17		8.45			
					15				9.04					
					20		8.1	8.1	8.90		7.8			
					25				8.75					
					0	15	14.1	14.1	14.59		14.1		V	
					5				14.27					
					10		13.75	13.75	14.18		13.45			
					15				14.07					
					20		13.1	13.1	13.95		12.8			
					25				13.80					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64	0.51	1	0.36		mA		
			0/10	0.5		10	1.6	1.3	2.6	0.9				
			0/15	1.5		15	4.2	3.4	6.8	2.4				
		HCF Types	0/5	0.4		5	0.52	0.44	1	0.36				
			0/10	0.5		10	1.3	1.1	2.6	0.9				
			0/15	1.5		15	3.6	3	6.8	2.4				
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5} \pm 0.1$		± 1	μ A		
		HCF Types	0/15		15		± 0.3		$\pm 10^{-5} \pm 0.3$		± 1			
C _I	Input Capacitance			Any Input				5	7.5			pF		

* T_{Low} = -55°C for HCC device, -40°C for HCF device.

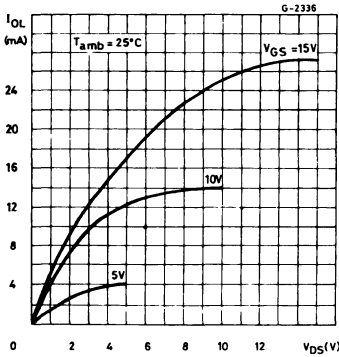
* T_{High} = +125°C for HCC device, +85°C for HCF device.

The Noise Margin for both "1" and "0" level is .1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

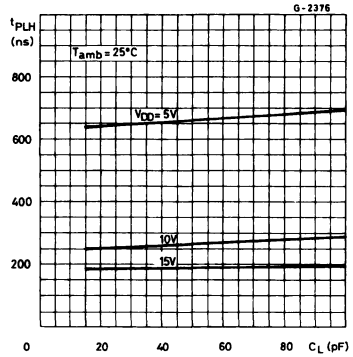
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\% / ^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time (data)		5		520	1040	ns
			10		210	420	
			15		150	300	
t_{PLH}	Propagation Delay Time (data)		5		660	1320	ns
			10		260	520	
			15		180	360	
t_{PHL}	Propagation Delay Time ($\overline{\text{BL}}$)		5		350	700	ns
			10		175	350	
			15		125	250	
t_{PLH}	Propagation Delay Time ($\overline{\text{BL}}$)		5		400	800	ns
			10		175	350	
			15		150	300	
t_{PHL}	Propagation Delay Time ($\overline{\text{LT}}$)		5		250	500	ns
			10		125	250	
			15		85	170	
t_{PLH}	Propagation Delay Time ($\overline{\text{LT}}$)		5		150	300	ns
			10		75	150	
			15		50	100	
t_{TLH}	Transition Time		5		40	80	ns
			10		30	60	
			15		20	50	
t_{THL}	Transition Time		5		125	310	ns
			10		75	185	
			15		65	160	
t_{setup}	Setup Time		5	150	75		ns
			10	70	35		
			15	40	20		
t_{hold}	Hold Time		5	0	-75		ns
			10	0	-35		
			15	0	-20		
t_w	Strobe Pulse Width		5	400	200		ns
			10	160	80		
			15	100	50		

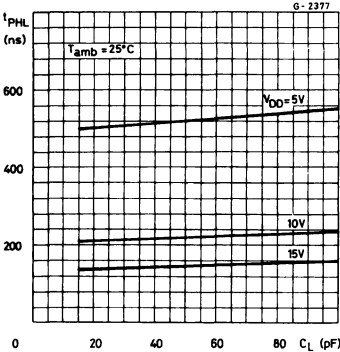
Typical Output Low (sink) Current Characteristics.



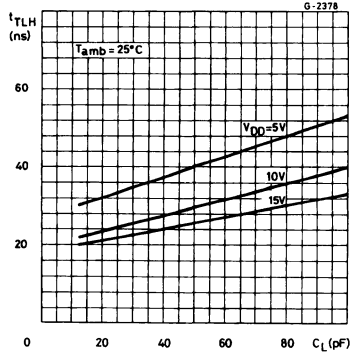
Typical data-to-output, low-to-high-level propagation delay time as a function of load capacitance.



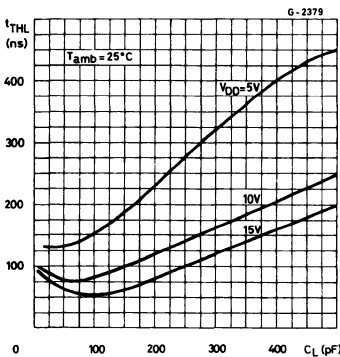
Typical data-to-output, high-to-low-level propagation delay time as a function of load capacitance.



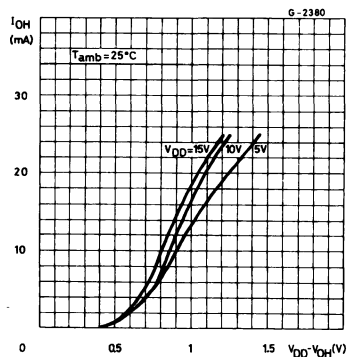
Typical low-to-high level transition time as a function of load capacitance.



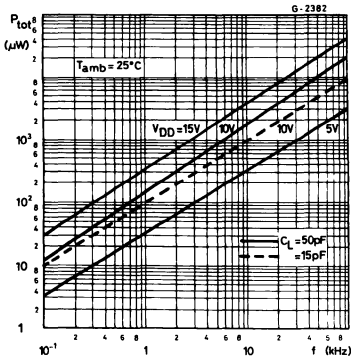
Typical high-to-low level transition time as a function of load capacitance.



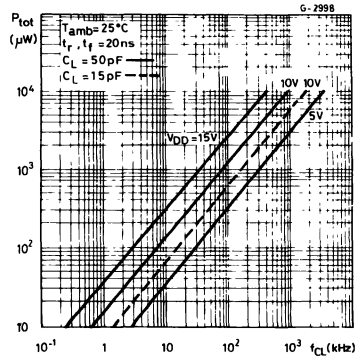
Typical Voltage drop (V_{DD} to output) vs. Output source Current as a Function of Supply.



Typical Dynamic Power Dissipation Characteristics.



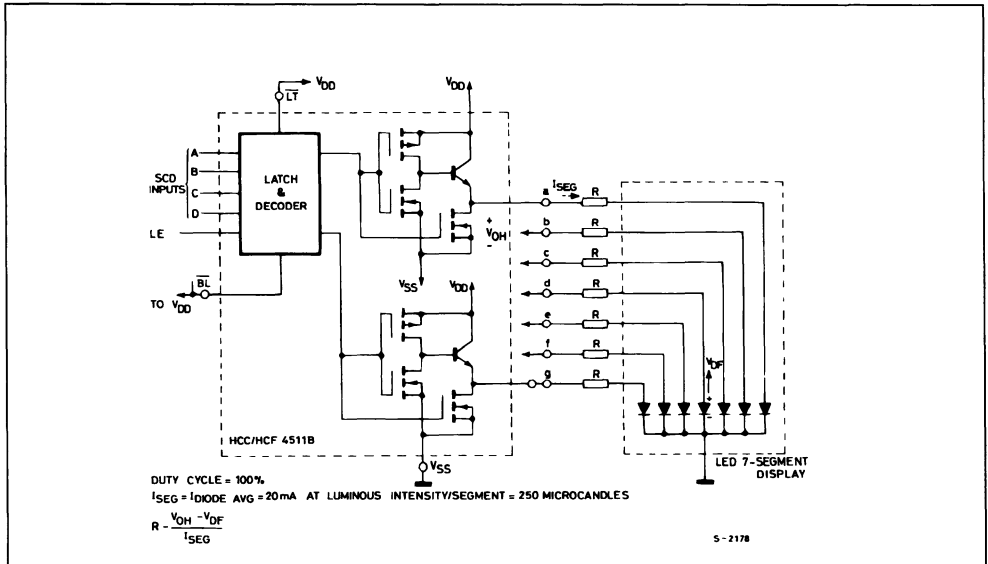
Derated Static Output Current Per Output.



Maximum continuous derated output current I_{OH} applies to a single output with all other outputs sourcing an equal amount of current at the supply voltages shown. Operation above the derating curve is not recommended.

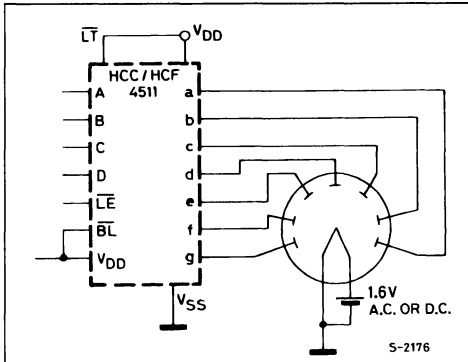
TYPICAL APPLICATIONS (interfacing with various displays)

DRIVING COMMON-CATHODE 7-SEGMENT LED DISPLAYS

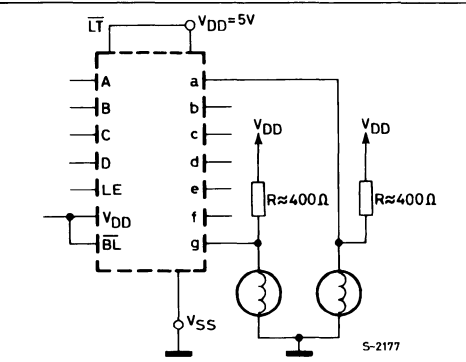


TYPICAL APPLICATIONS (continued)

Driving Low-voltage Fluorescent Displays.



Driving Incandescent Displays.

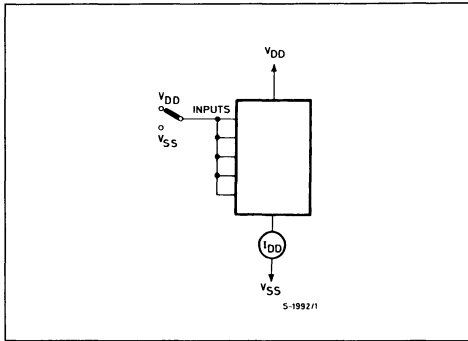


2 of 7 Segments Shown Connected
Resistors R from VDD VDD to each 7-segment driver output are chosen to keep all Numitron segments slightly on and warm.

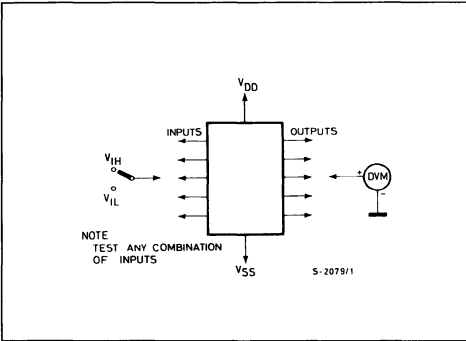
A medium-brightness intensity display can be obtained with low-voltage fluorescent displays such as the Tung-Sot Digivac S/G series.

TEST CIRCUITS

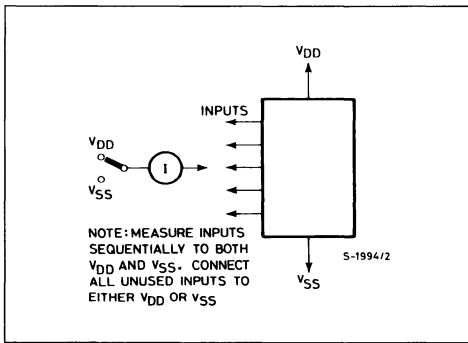
Quiescent Device Current.



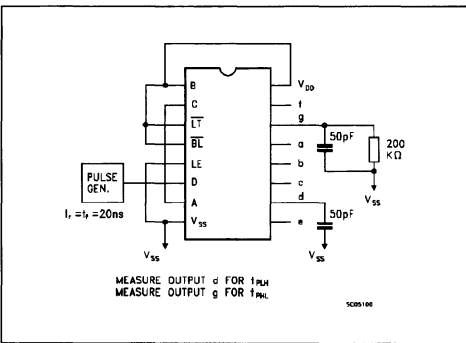
Noise Immunity.



Input Leakage Current.

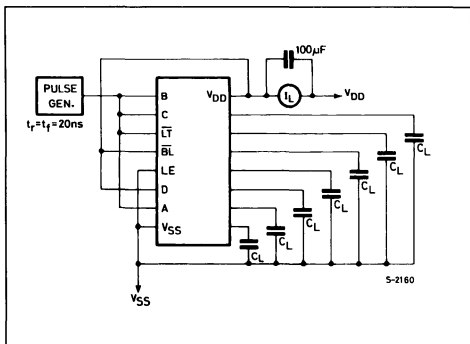


Data Propagation Delay.



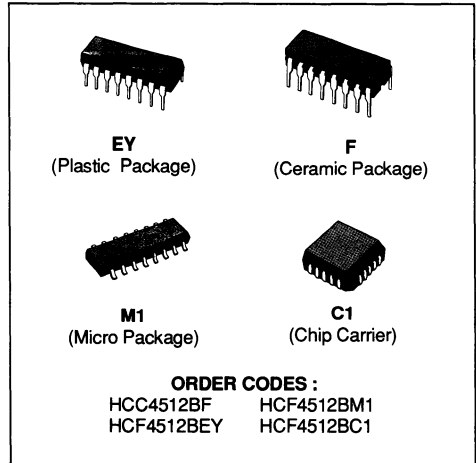
TEST CIRCUITS (continued)

Dynamic Power dissipation.



8-CHANNEL DATA SELECTOR

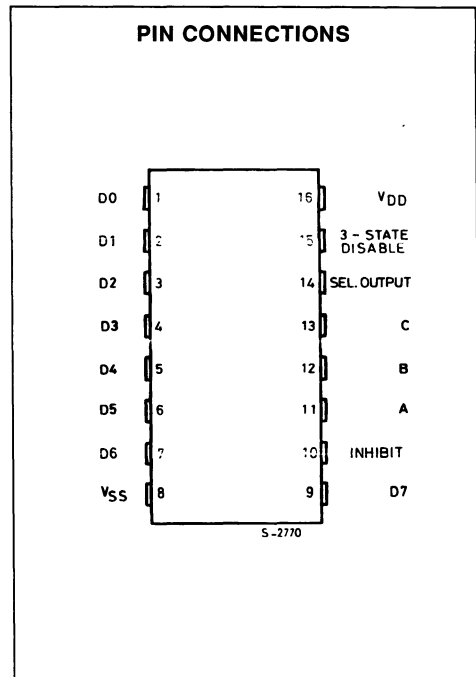
- 3-STATE OUTPUT
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



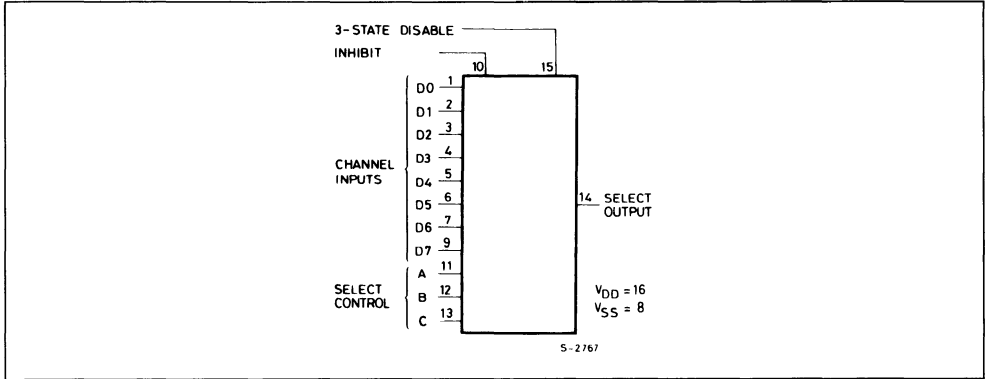
DESCRIPTION

The **HCC4512B** (extended temperature range) and **HCF4512B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4512B** is an 8-channel data selector featuring a three-state output that can interface directly with, and drive, data lines of bus-oriented systems.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature . HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

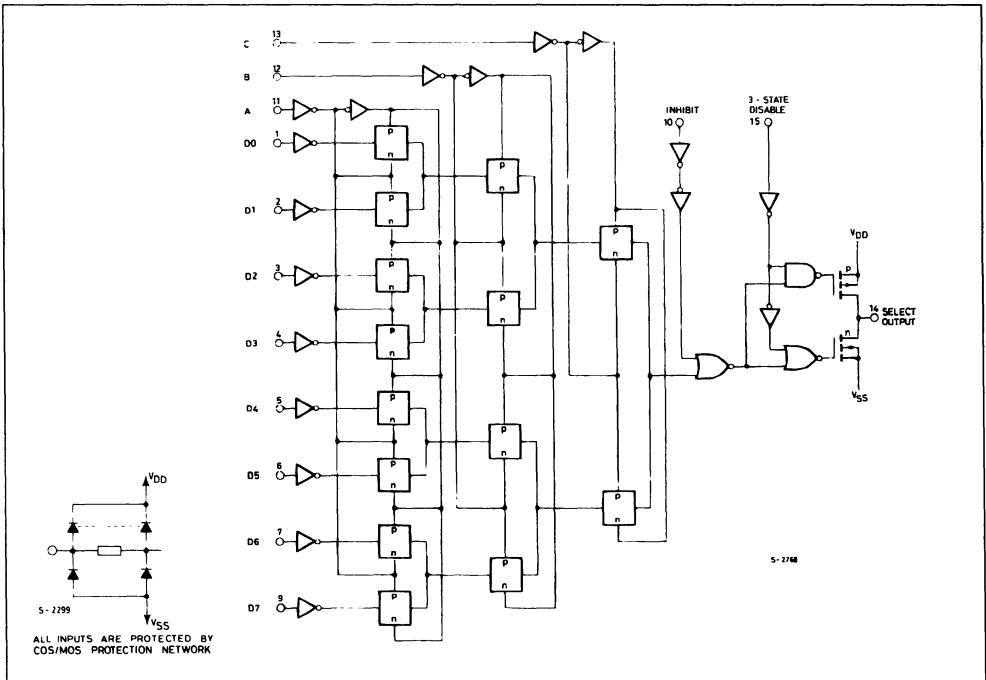
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to + 18 3 to + 15	V V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature . HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

TRUTH TABLE

Sel. Cont.			Inh.	3-State Disable	Sel. Output
A	B	C			
0	0	0	0	0	D0
1	0	0	0	0	D1
0	1	0	0	0	D2
1	1	0	0	0	D3
0	0	1	0	0	D4
1	0	1	0	0	D5
0	1	1	0	0	D6
1	1	1	0	0	D7
X	X	X	1	0	0
X	X	X	X	1	High Z

1 = High Level 0 = Low Level X = Don't Care

LOGIC DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C		T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5	150	μ A
			0/10			10		10		0.04	10	300	
			0/15			15		20		0.04	20	600	
		0/20			20		100		0.08	100	3000		
		HCF Types	0/ 5			5		20		0.04	20	150	
			0/10			10		40		0.04	40	300	
0/15				15		80		0.04	80	600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95		4.95		V	
		0/10		< 1	10	9.95		9.95		9.95			
		0/15		< 1	15	14.95		14.95		14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05		0.05		0.05	V	
		10/0		< 1	10		0.05		0.05		0.05		
		15/0		< 1	15		0.05		0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5		3.5		V	
			1/9	< 1	10	7		7		7			
			1.5/13.5	< 1	15	11		11		11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5		1.5		1.5	V	
			9/1	< 1	10		3		3		3		
			13.5/1.5	< 1	15		4		4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36	
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9	
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1	
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36	
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9			
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1	\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3	\pm 1	
I _{O max}	3-State Output Leakage Current	HCC Types	0/18	0/18		18		\pm 0.4		\pm 10 ⁻⁴	\pm 0.4	\pm 12	μ A
		HCF Types	0/18	0/18		18		\pm 1.0		\pm 10 ⁻⁴	\pm 1.0	7.5	
C _I	Input Capacitance			Any Input					5	7.5		pF	

* T_{Low}= - 55°C for HCC device : - 40°C for HCF device

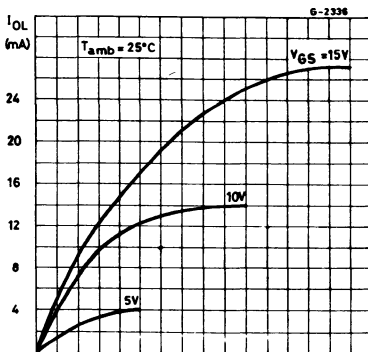
* T_{High}= + 125°C for HCC device + 85°C for HCF device

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

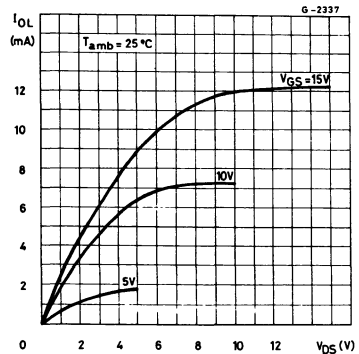
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time Inhibit to Output		5		140	280	ns
			10		70	140	
			15		50	100	
t_{PHL} , t_{PLH}	Propagation Delay Time "A" Select to Output		5		200	400	ns
			10		85	170	
			15		60	120	
t_{PHL} , t_{PLH}	Propagation Delay Time Data to Output		5		180	360	ns
			10		75	150	
			15		55	110	
t_{PZL} , t_{PLZ} t_{PHZ} , t_{PZH}	3-state Disable Delay Time		5		60	120	ns
			10		30	60	
			15		20	40	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

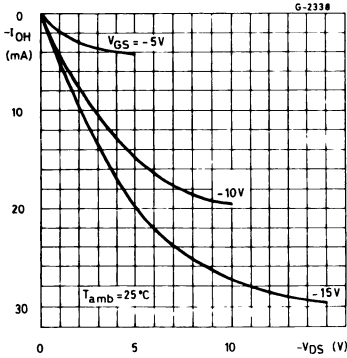
Typical Output Low (sink) Current Characteristics.



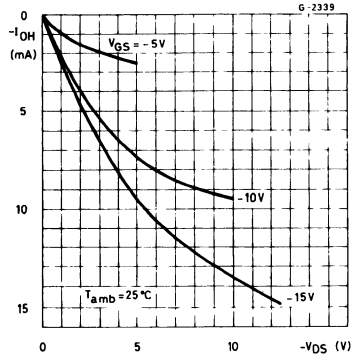
Minimum Output Low (sink) Current Characteristics.



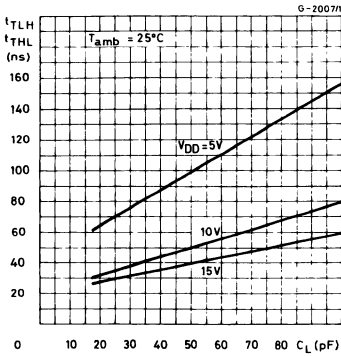
Typical Output High (source) Current Characteristics.



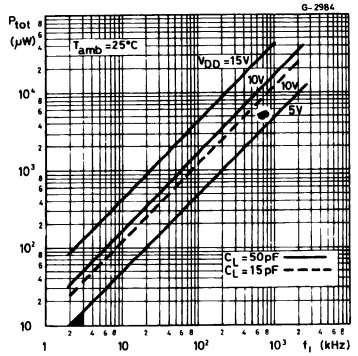
Minimum Output High (source) Current Characteristics.



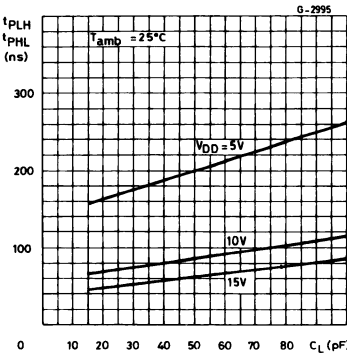
Typical Transition Time vs. Load Capacitance.



Typical Dynamic Power Dissipation vs. Input Frequency.

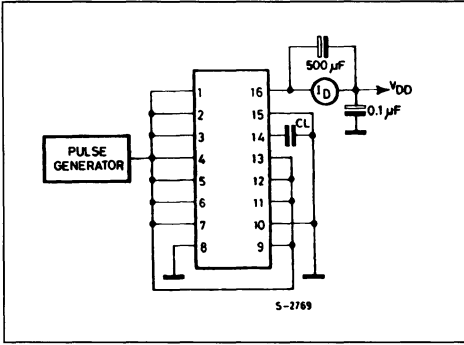


Typical Propagation Delay Time as a Function of Load Capacitance ("A" select to output).

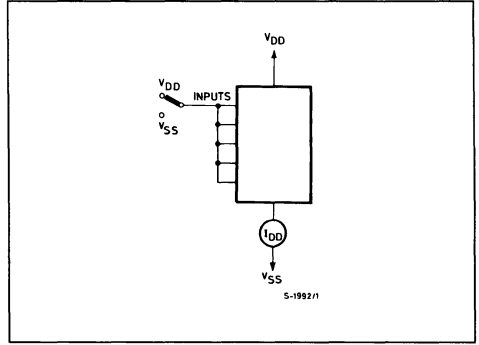


TEST CIRCUITS

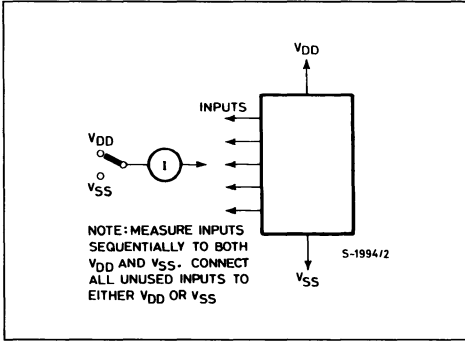
Dynamic Power Dissipation Test Circuit.



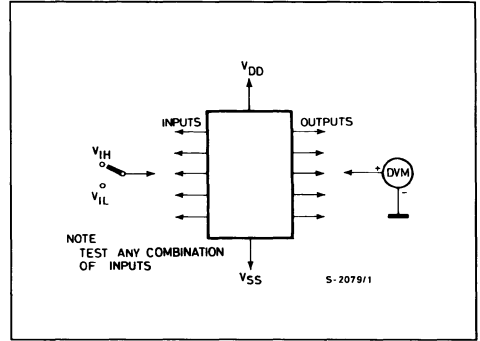
Quiescent Device Current Test Circuit.



Input Current Test Circuit.



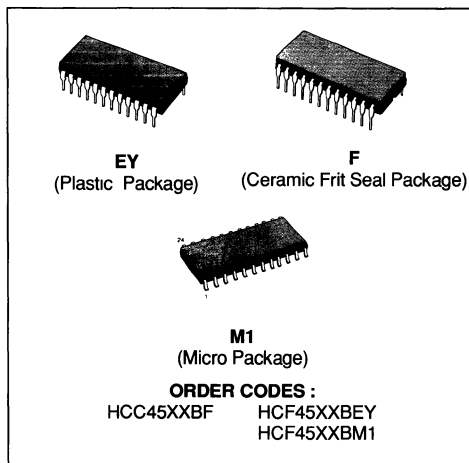
Input Voltage Test Circuit.



4-BIT LATCH/4-TO-16 LINE DECODER

HCC/HCF4514B OUTPUT "HIGH" ON SELECT
HCC/HCF4515B OUTPUT "LOW" ON SELECT

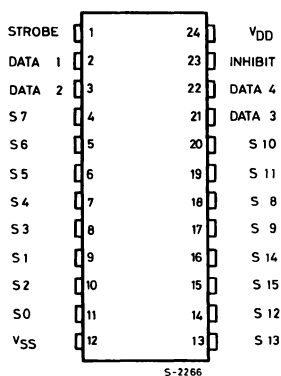
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STROBED INPUT LATCH
- INHIBIT CONTROL
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



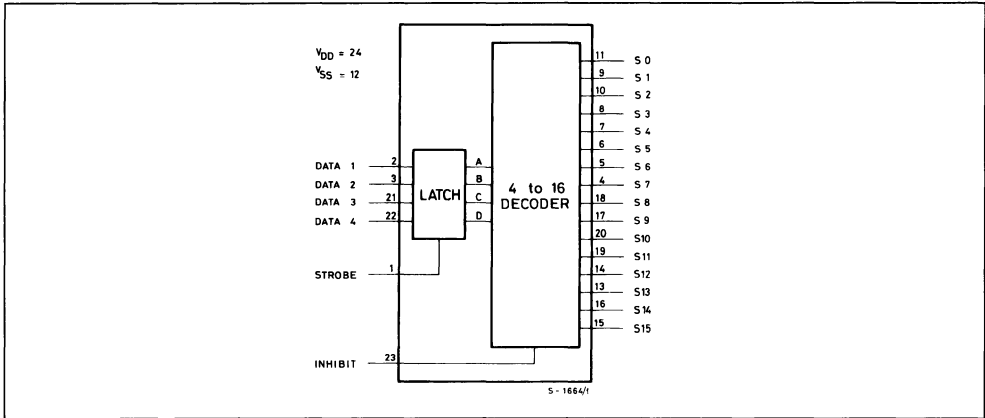
DESCRIPTION

The **HCC 4514B/HCC4515B** (extended temperature range) and the **HCF 4514B/HCF4515B** (intermediate temperature range) are monolithic integrated circuits available in 24-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4514B/4515B** consisting of a 4-bit strobed latch and a 4 to 16 line decoder. The latches hold the last input data presented prior to the strobe transition from 1 to 0. Inhibit control allows all outputs to be placed at 0 (**HCC/HCF4514B**) or 1 (**HCC/HCF4515B**) regardless of the state of the data or strobe inputs. The decode truth table indicates all combinations of data inputs and appropriate selected outputs.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

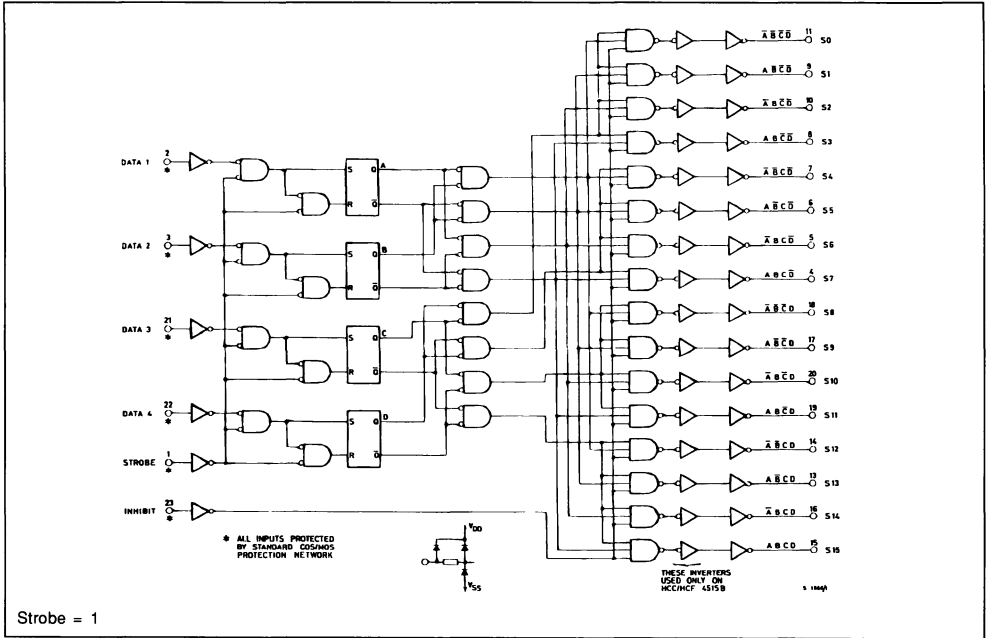
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM AND TRUTH TABLE

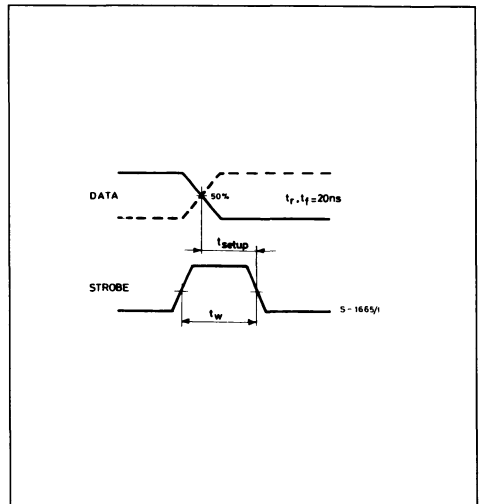


Inhibit	Data Inputs				Selected Output HCC/HCF 4514B = Logic 1 (High) HCC/HCF 4515B = Logic 0 (Low)
	D	C	B	A	
0	0	0	0	0	S0
0	0	0	0	1	S1
0	0	0	1	0	S2
0	0	0	1	1	S3
0	0	1	0	0	S4
0	0	1	0	1	S5
0	0	1	1	0	S6
0	0	1	1	1	S7
0	1	0	0	0	S8
0	1	0	0	1	S9
0	1	0	1	0	S10
0	1	0	1	1	S11
0	1	1	0	0	S12
0	1	1	0	1	S13
0	1	1	1	0	S14
0	1	1	1	1	S15
1	X	X	X	X	All Outputs = 0, HCC/HCF 4514B All Outputs = 1, HCC/HCF 4515B

X = Don't Care
1 = high

WAVEFORMS

Setup Time and Strobe Pulse Width.



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low}= - 55°C for HCC device - 40°C for HCF device.

* T_{High}= + 125°C for HCC device + 85°C for HCF device

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

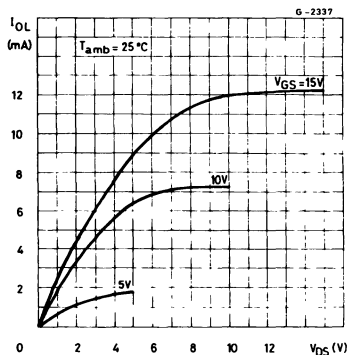
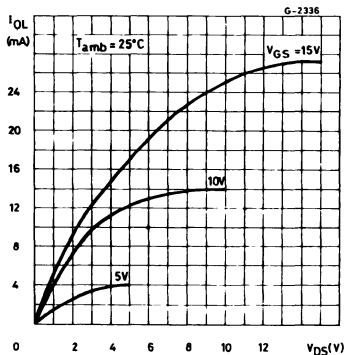
DYNAMIC ELECTRICAL CHARACTERISTICS

($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, all input rise and fall time = 20ns)

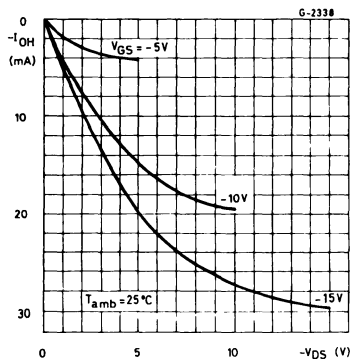
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time	Strobe or Data	5	485	970	ns	
			10	185	370		
			15	135	270		
		Inhibit	5	250	500	ns	
			10	110	220		
			15	85	170		
t_{THL} , t_{THL}	Transition Time		5	100	200	ns	
			10	50	100		
			15	40	80		
t_w	Strobe Pulse Width		5	250	125	ns	
			10	100	50		
			15	75	40		
t_{setup}	Setup Time		5	150	75	ns	
			10	70	35		
			15	40	20		

Typical Output Low (sink) Current Characteristics.

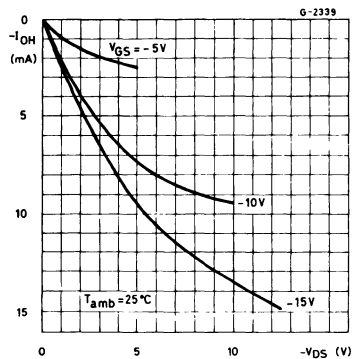
Minimum Output Low (sink) Current Characteristics.



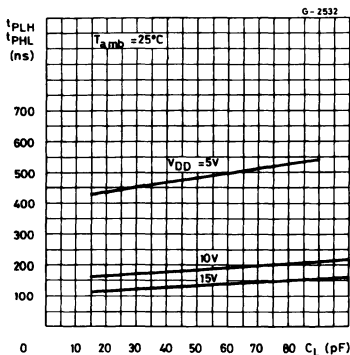
Typical Output High (source) Current Characteristics.



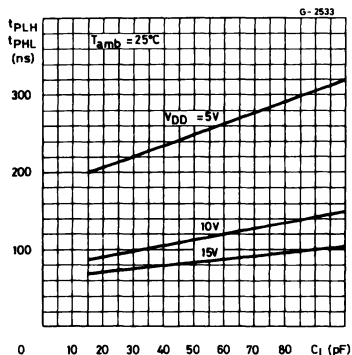
Minimum Output High (source) Current Characteristics.



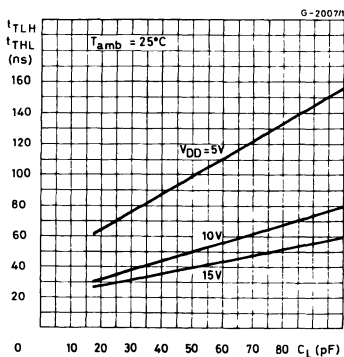
Typical Strobe or Data Propagation Delay Time vs. Load Capacitance.



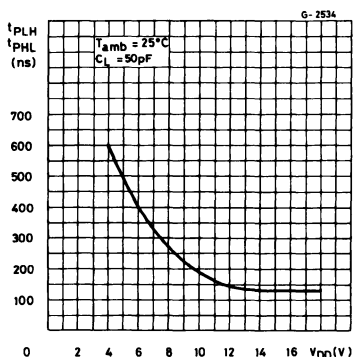
Typical Inhibit Propagation Delay Time vs. Load Capacitance.



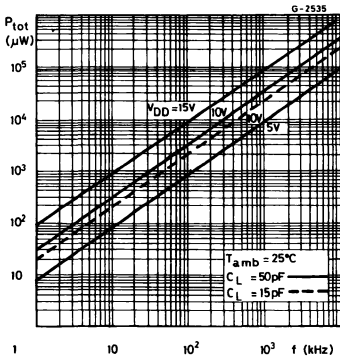
Typical Transition Time vs. Load Capacitance.



Typical Strobe or Data Propagation Delay Time vs. Supply Voltage.

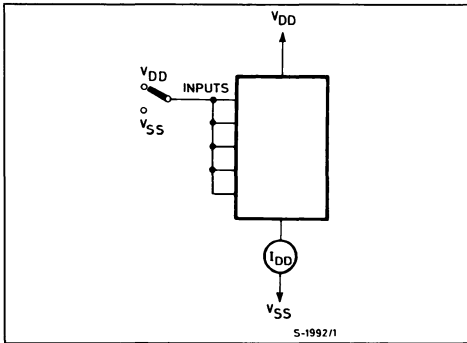


Typical Power Dissipation vs. Frequency.

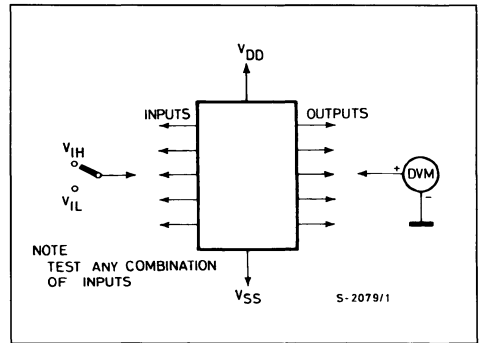


TEST CIRCUITS

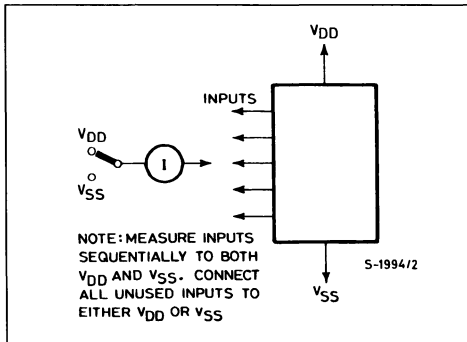
Quiescent Device Current.



Noise Immunity.

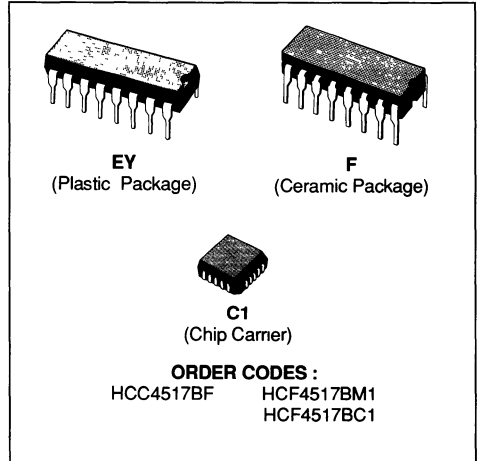


Input Leakage Current.



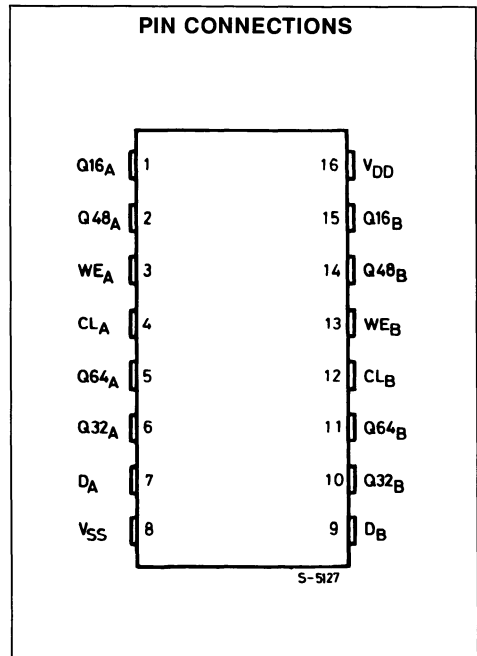
DUAL 64-STAGE STATIC SHIFT REGISTER

- CLOCK FREQUENCY 12MHz (TYP.) AT $V_{DD} = 10V$
- SCHMITT TRIGGER CLOCK INPUTS ALLOW OPERATION WITH VERY SLOW CLOCK RISE AND FALL TIMES
- THREE-STATE OUTPUTS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURREN OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

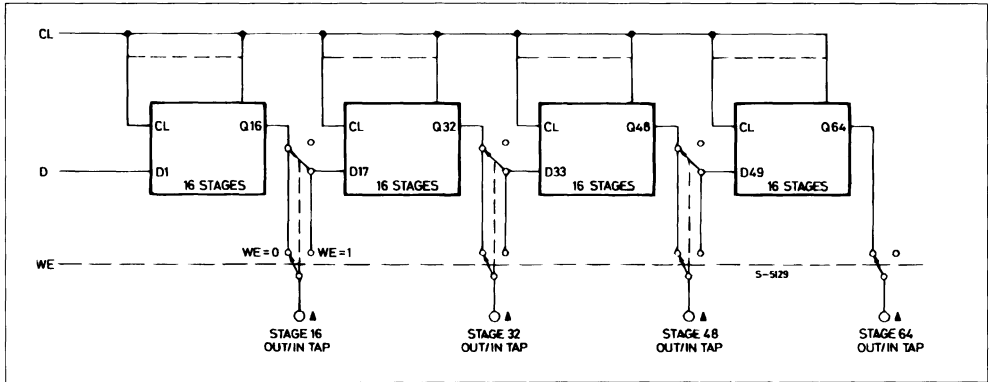

DESCRIPTION

The **HCC4517B** (extended temperature range) and **HCF4517B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package.

The **HCC/HCF4517B** dual 64-stage static shift register consists of two independent registers each having a clock, data, and write enable input and outputs accessible at taps following the 16th, 32nd, 48th, and 64th stages. These taps also serve as input points allowing data to be inputted at the 17th, 33rd, and 49th stages when the write enable input is a logic 1 and the clock goes through a low-to-high transition. The truth table indicates how the clock and write enable inputs control the operation of the **HCC/HCF4517B**. Inputs at the intermediate taps allow entry of 64 bits into the register with 16 clock pulses. The 3-state outputs permit connection of this device to an external bus.



FUNCTIONAL DIAGRAM (one half)



ABSOLUTE MAXIMUM RATINGS

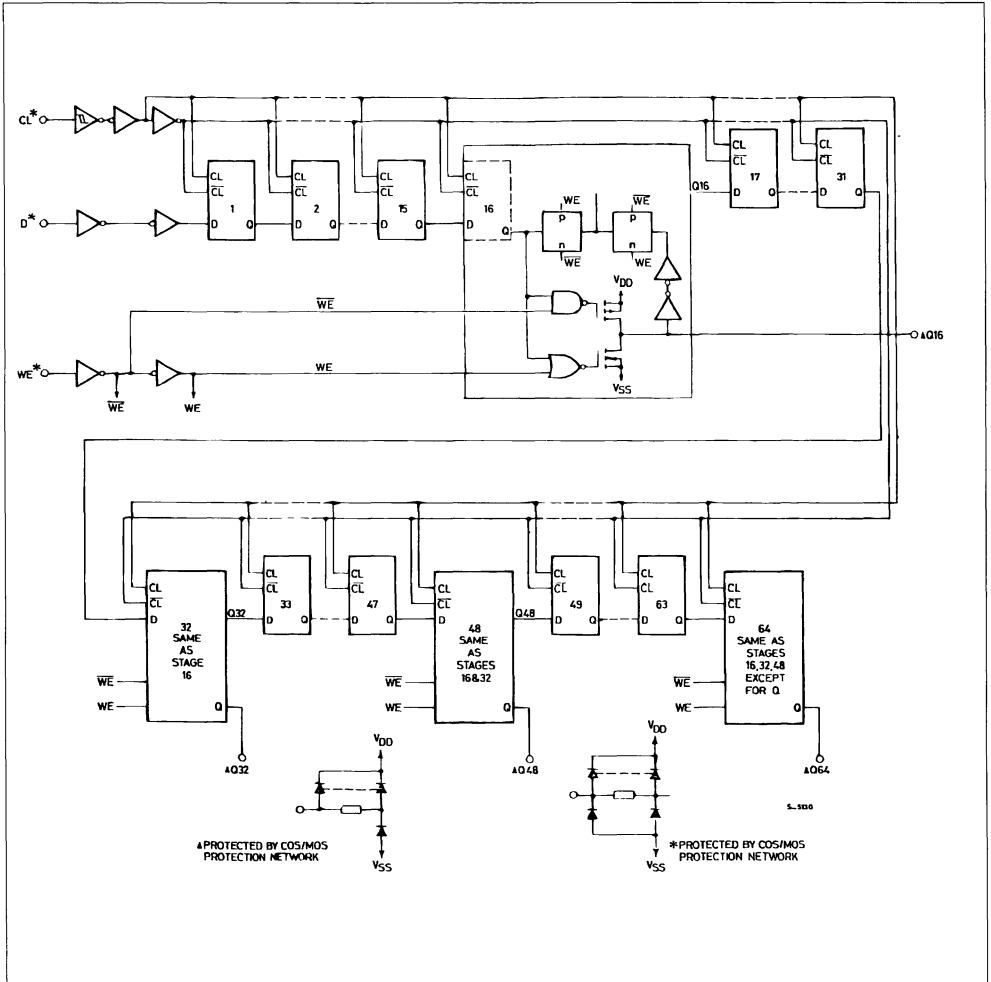
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{Tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
* All voltages are with respect to V_{SS} (GND)

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAM AND TRUTH TABLE



Clock	Write Enable	Data	Stage 16 Tap	Stage 32 Tap	Stage 48 Tap	Stage 64 Tap
0	0	X	Q16	Q32	Q48	Q64
0	1	X	Z	Z	Z	Z
1	0	X	Q16	Q32	Q48	Q64
1	1	X	Z	Z	Z	Z
	0	Di In	Q16	Q32	Q48	Q64
	1	Di In	D17 In	D33 In	D49 In	Z
	0	X	Q16	Q32	Q48	Q64
	1	X	Z	Z	Z	Z

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		0/20			20		100		0.08	100		3000		
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage	0/5/4.5		< 1	5	3.5		3.5			3.5		V	
		1/9		< 1	10	7		7			7			
		1.5/13.5		< 1	15	11		11			11			
V _{IL}	Input Low Voltage	4.5/0.5		< 1	5		1.5			1.5		1.5	V	
		9/1		< 1	10		3			3		3		
		13.5/1.5		< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
		0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
I _{OH} , I _{OL}	3-State Output Leakage Current	HCC Types	0/18			18		\pm 0.4		\pm 10 ⁻⁴	\pm 0.4		\pm 12	μ A
		HCF Types	0/18			15		\pm 1.0		\pm 10 ⁻⁴	\pm 1.0		\pm 7.5	
C _I	Input Capacitance			Any Input					5	7.5			pF	

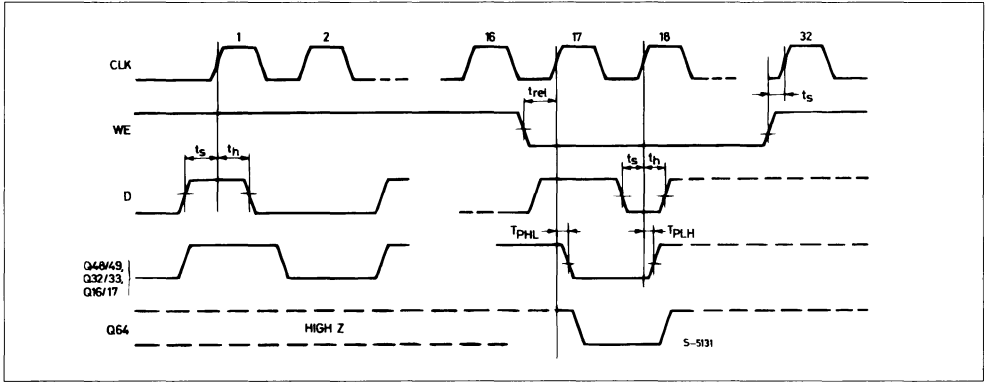
* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min with V_{DD} = 15V,

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, Input $t_r, t_f = 20\text{ns}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$)

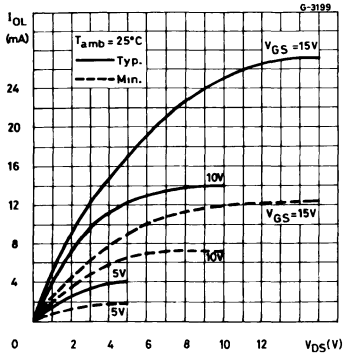
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}, t_{PLH}	Propagation Delay Time : CL to Bit 16 Tap		5		200	400	ns
			10		110	220	
			15		90	180	
t_{PLZ}, t_{PHZ} t_{PZL}, t_{PZH}	3-State Output WE to Bit 16 Tap (see note)		5		75	150	ns
			10		40	80	
			15		30	60	
t_{THL}, t_{TLH}	Output Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Write Enable to Clock		5	- 100	- 50		ns
			10	- 50	- 25		
			15	- 30	- 15		
t_{setup}	Data to Clock		5	- 100	- 50		ns
			10	- 60	- 30		
			15	- 30	- 15		
	Write Enable to Clock Release Time		5		50	100	ns
			10		25	50	
			15		20	40	
t_{hold}	Data to Clock		5		100	200	ns
			10		50	100	
			15		25	50	
t_w	Minimum Clock Pulse Width		5		90	180	ns
			10		40	80	
			15		25	50	
f_{CL}	Maximum Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8	15		
t_r, t_f	Maximum Clock Input Rise or Fall Time		5	UNLIMITED			μs
			10				
			15				

Note Measured at the point of 10% change in output load of 50pF, $R_L = 1\text{k}\Omega$ to V_{DD} for t_{PZL}, t_{PLZ} and $R_L = 1\text{k}\Omega$ to V_{SS} for t_{PHZ}

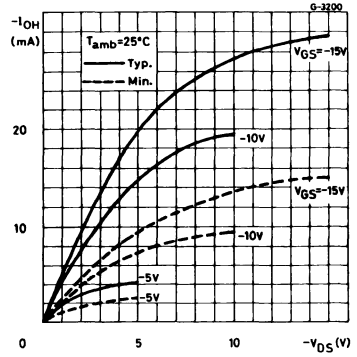
WAVEFORMS



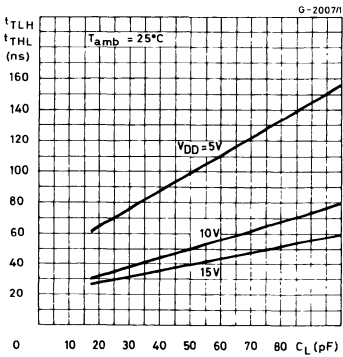
Output Low (sink) Current Characteristics.



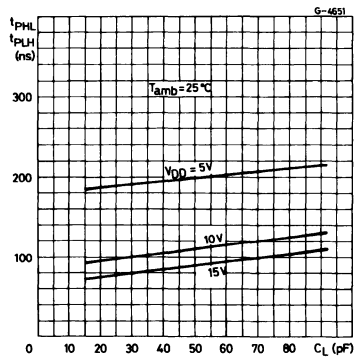
Output High (source) Current Characteristics.



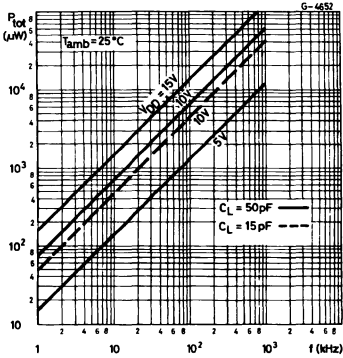
Typical Transition Time vs. Load Capacitance.



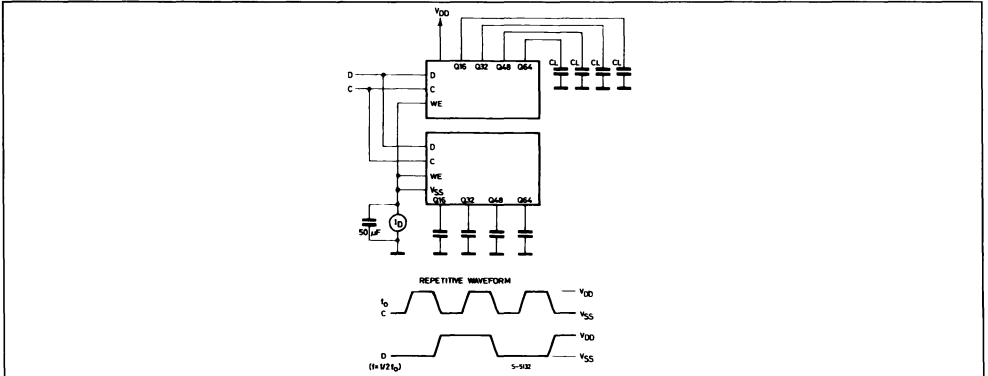
Typical Propagation Delay Time vs. Load Capacitance.



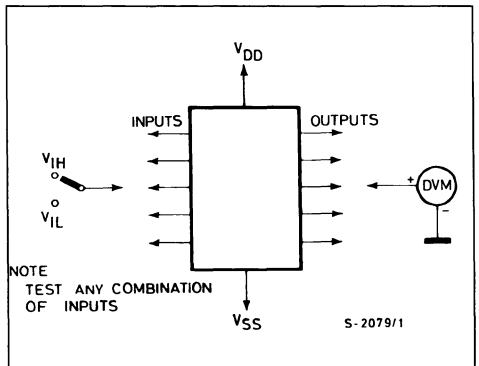
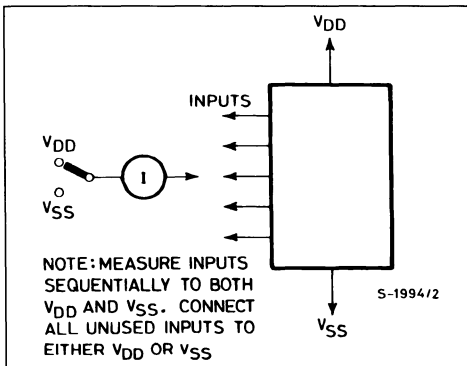
Typical Dynamic Power Dissipation vs. Frequency.



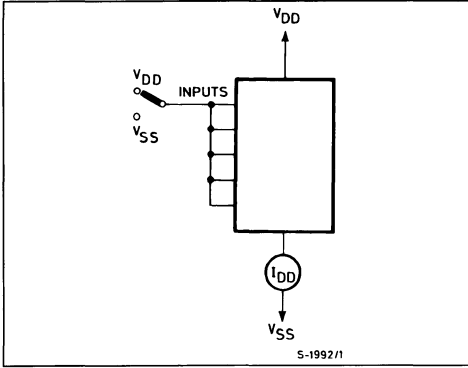
Dynamic Power Dissipation and Waveforms.



TEST CIRCUITS



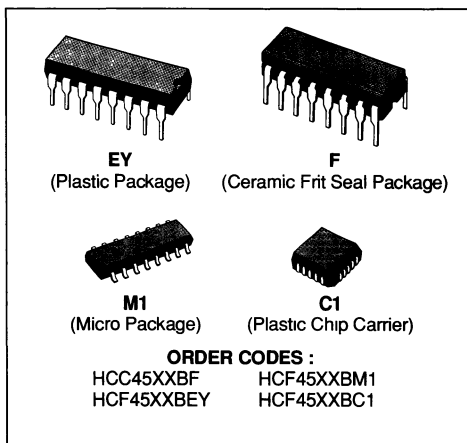
TEST CIRCUITS (continued)



DUAL UP-COUNTERS

HCC/HCF4518B DUAL BCD UP-COUNTER
HCC/HCF4520B DUAL BINARY UP-COUNTER

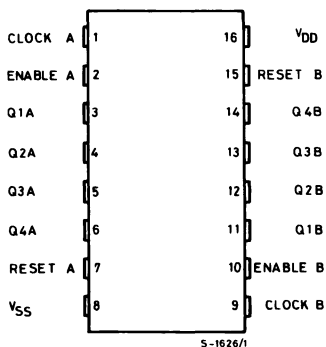
- MEDIUM-SPEED OPERATION – 6MHz TYP. CLOCK FREQUENCY AT 10V
- POSITIVE - OR NEGATIVE - EDGE TRIGGERING
- SYNCHRONOUS INTERNAL CARRY PROPAGATION
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



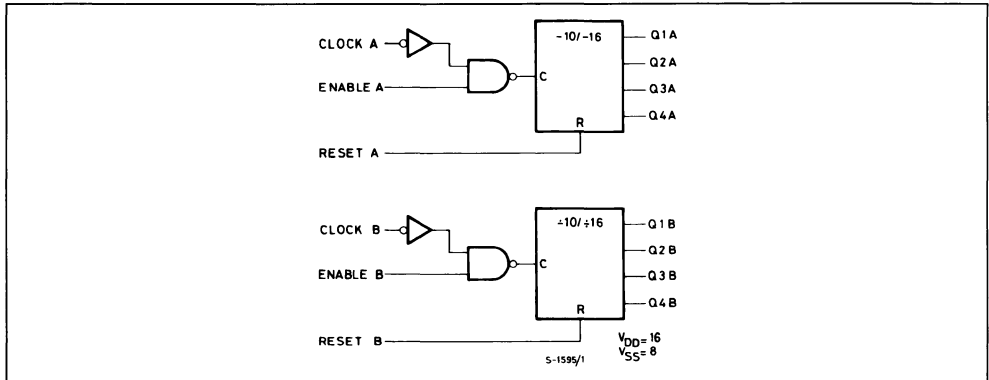
DESCRIPTION

The **HCC4518B/4520B** (extended temperature range) and **HCF4518B/4520B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF4518B** Dual BCD Up Counter and **HCC/HCF4520B** Dual Binary Up Counter each consist of two identical, internally synchronous 4-stage counters. The counter stages are D-type flip-flops having interchangeable Clock and Enable lines for incrementing on either the positive-going or negative-going transition. For single-unit operation the Enable input is maintained "high" and the counter advances on each positive-going transition of the Clock. The counters are cleared by high levels on their Reset lines. The counter can be cascaded in the ripple mode by connecting Q4 to the enable input of the subsequent counter while the clock input of the latter is held low.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

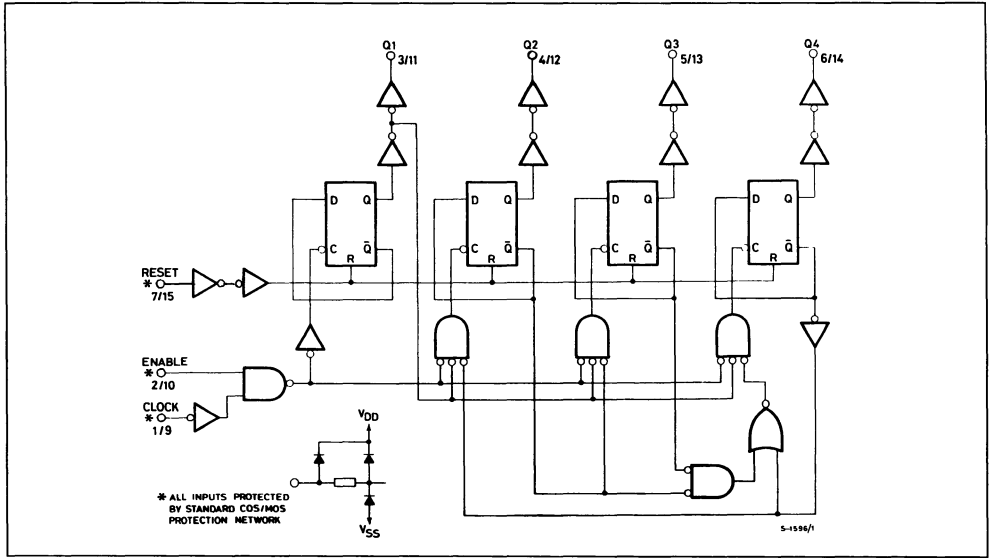
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

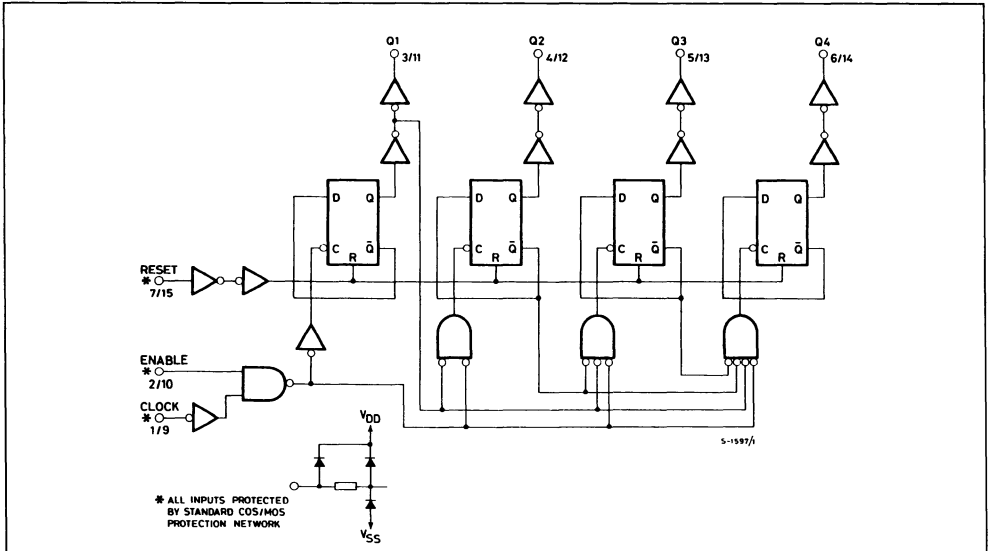
Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAMS (for one of two identical counter)

Decade Counter for 4518B.



Binary Counter for 4520B.

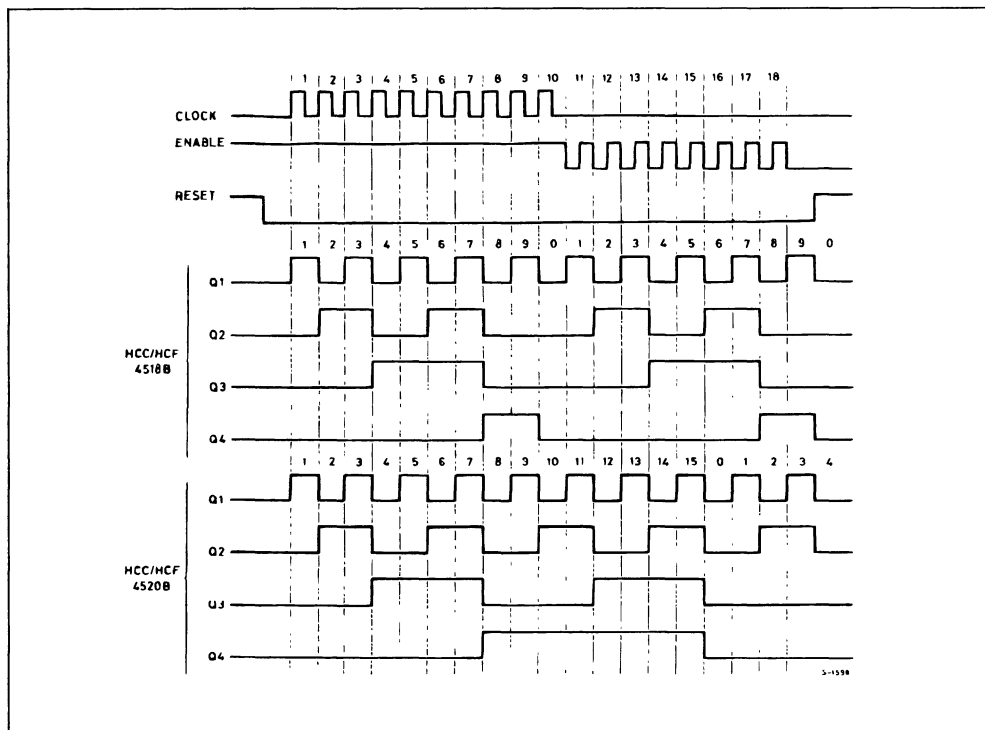


TRUTH TABLE

Clock	Enable	Reset	Action
	1	0	Increment Counter
0		0	Increment Counter
	X	0	No Change
X		0	No Change
	0	0	No Change
1		0	No Change
X	X	1	Q1 Thru Q4 = 0

X = Don't Care Logic 1 = High State Logic 0 = Low

TIMING DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

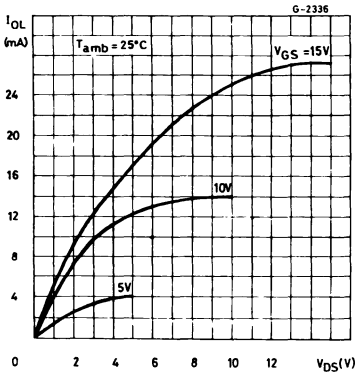
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = -55°C for HCC device . -40°C for HCF device.* T_{High} = +125°C for HCC device +85°C for HCF device.The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

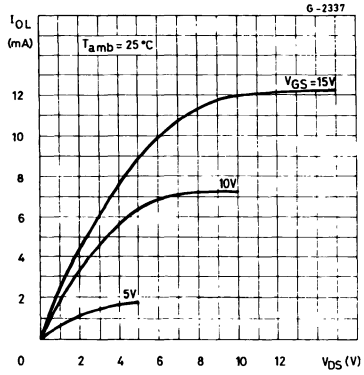
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time (clock or enable to output)		5		280	560	ns
			10		115	230	
			15		80	160	
t_{PLH} , t_{PHL}	Propagation Delay Time (reset to output)		5		330	650	ns
			10		130	225	
			15		90	170	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_W	Clock Pulse Width		5	200	100		ns
			10	100	50		
			15	70	35		
t_W	Reset Pulse Width		5	250	125		ns
			10	110	55		
			15	80	40		
t_W	Enable Pulse Width		5	400	200		ns
			10	200	100		
			15	140	70		
t_r , t_f	Clock or Enable Rise and Fall Time		5			15	μs
			10			15	
			15			5	
f_{max}	Maximum Clock Frequency		5	1.5	3		MHz
			10	3	6		
			15	4	8		
t_r , t_f	Clock Input Rise or Fall Time		5			15	μs
			10			5	
			15			5	

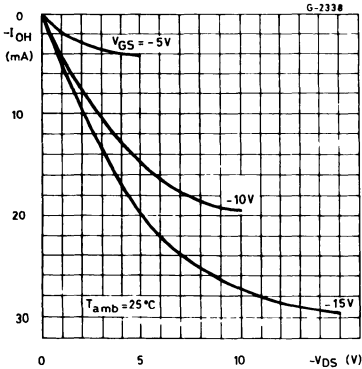
Typical Output Low (sink) Current Characteristics.



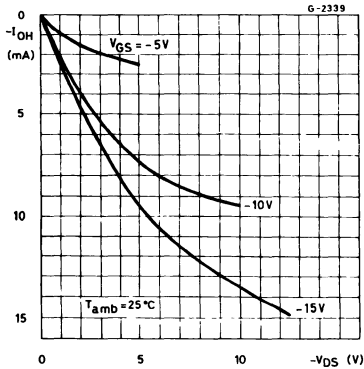
Minimum Output Low (sink) Current Characteristics.



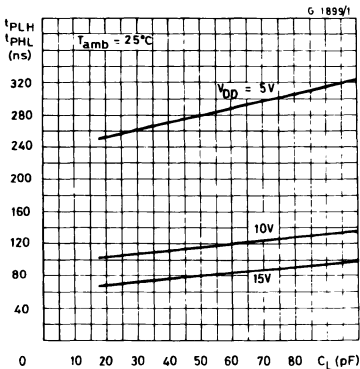
Typical Output High (source) Current Characteristics.



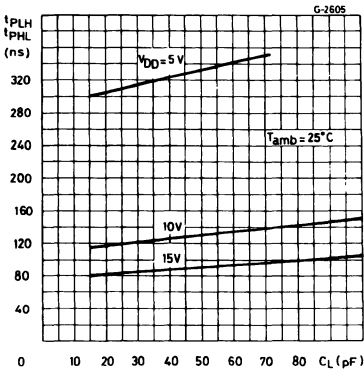
Minimum output High (source) Current Characteristics.



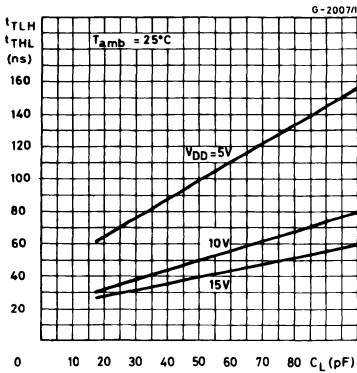
Typical Propagation Delay vs. Load Capacitance, Reset to output.



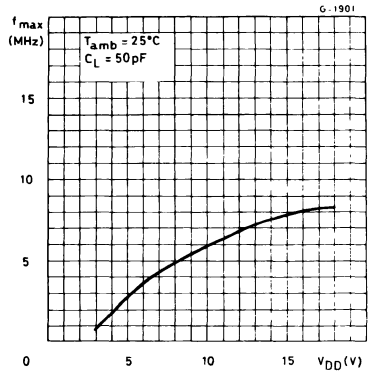
Typical Propagation Delay Time vs. Load Capacitance, Clock or Enable to Output.



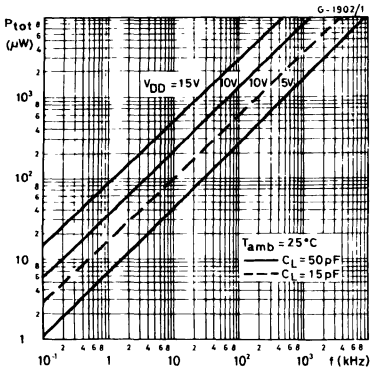
Typical Transition Time vs. load Capacitance.



Typical Maximum-clock Frequency vs. Supply Voltage.

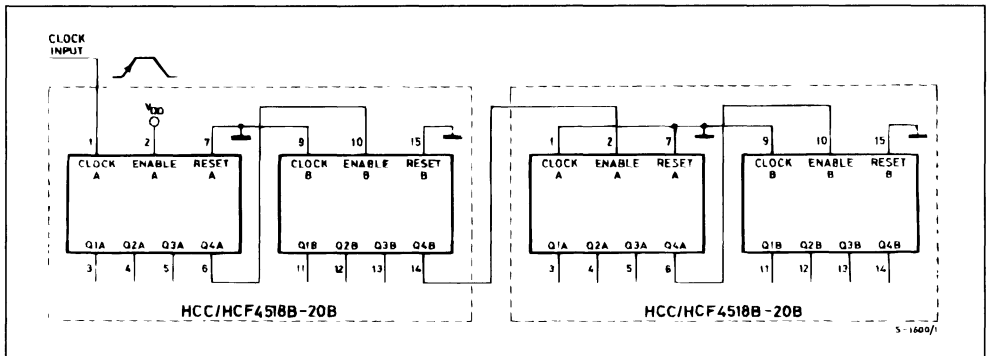


Typical Power Dissipation/Counter vs. Frequency.

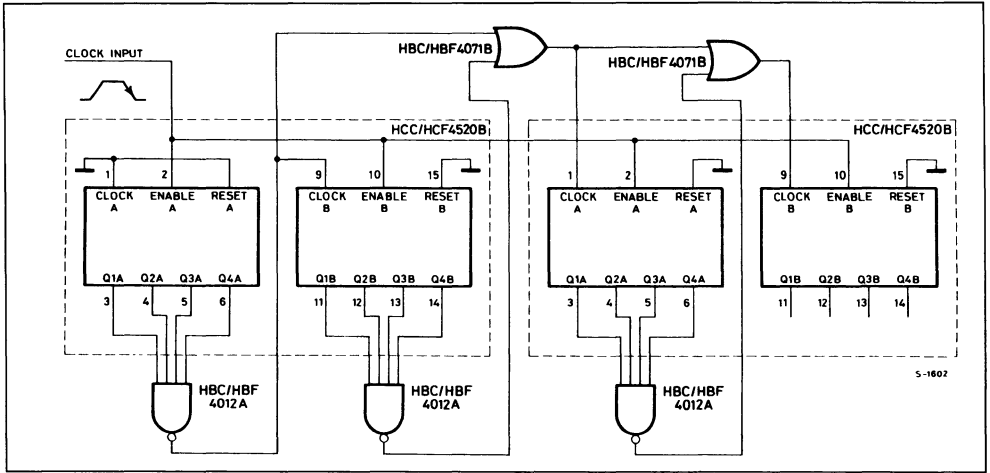


TYPICAL APPLICATIONS

RIPPLE CASCADING OF FOUR COUNTERS WITH POSITIVE-EDGE TRIGGERING.

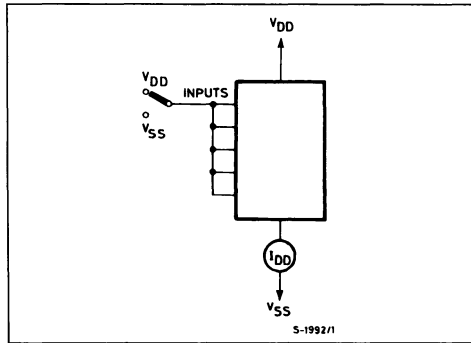


SYNCHRONOUS CASCADING OF FOUR BINARY COUNTERS WITH NEGATIVE-EDGE TRIGGERING.

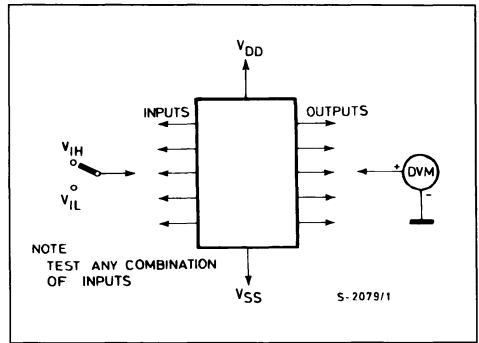


TEST CIRCUITS

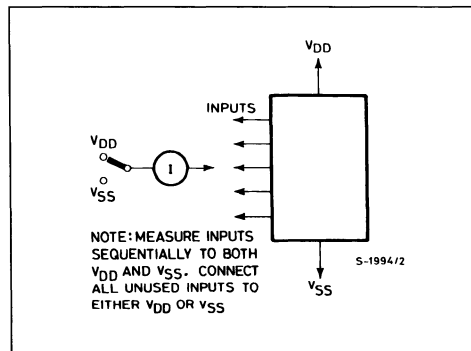
Quiescent Device Current.



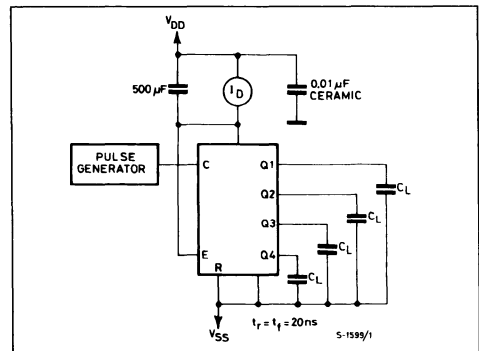
Noise Immunity.



Input Leakage Current.



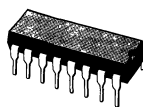
Dynamic Power Dissipation.



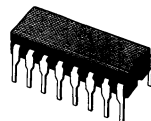
4 - BIT AND/OR SELECTOR

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SUPPLY VOLTAGE RANGE 3V TO 18V
- SINGLE SUPPLY VOLTAGE - POSITIVE OR NEGATIVE
- LOGIC SWING INDEPENDENT OF FANOUT



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)

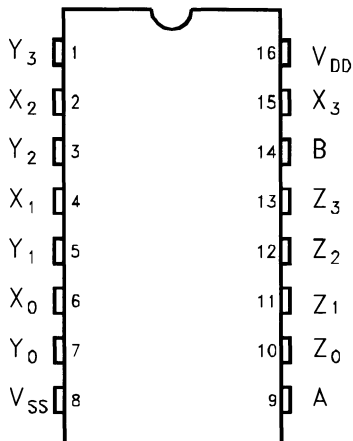


C1
(Plastic Chip Carrier)

ORDER CODES :

HCC4519 BF HCF4519 BM1
HCF4519 BEY HCF4519 BC1

PIN CONNECTION (top view)



PC10010

DESCRIPTION

The **HCC4519B** and **HCF4519B** are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages or in 16-pin SO micro-packages.

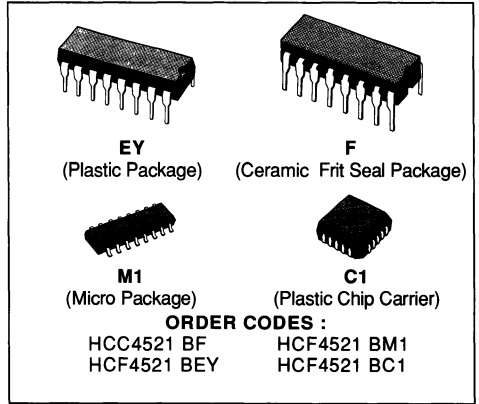
The **HCC4519B** and **HCF4519B** can be used for three different functions. They are :

- 1) a 4-bit and/or selector,
- 2) a quad 2-channel data selector,
- 3) a quad exclusive "NOR" gate.

24 - STAGE FREQUENCY DIVIDER

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- VOLTAGE SUPPLY RANGE 3V TO 18V
- ALL STAGES ARE RESETTABLE
- RESET DISABLES THE RC OSCILLATOR FOR LOW STANDBY POWER DRAIN
- RC AND CRYSTAL OSCILLATOR OUTPUT ARE CAPABLE OF DRIVING EXTERNAL LOADS

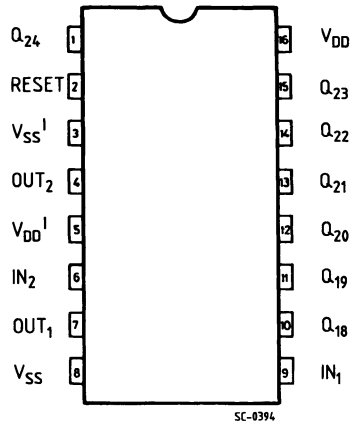


DESCRIPTION

The HCC4521B and HCF4521B are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages and plastic micro packages.

The HCC4521B and HCF4521B have a chain of 24 flip-flops with an input circuit that allows three modes of operation. The input circuit functions as a crystal or an RC oscillator or as an input buffer for an external oscillator. Each flip-flop performs a divide-by-two function giving a total count of $2^{24} = 16,777,216$. The count advances on the negative going edge of the clock. Access is available to the final seven stages giving the device added flexibility.

PIN CONNECTION (top view)

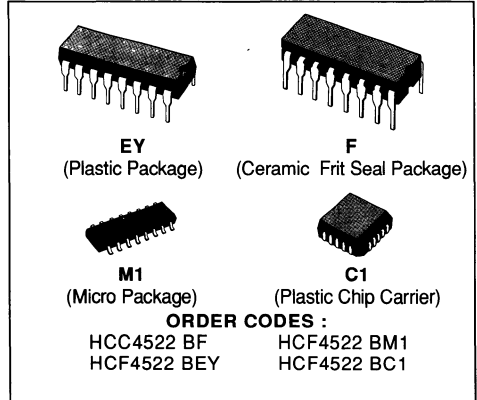




PROGRAMMABLE BCD DIVIDER-BY-N COUNTER

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SUPPLY VOLTAGE RANGE 3V TO 18V
- INTERNALLY SYNCHRONOUS FOR HIGH INTERNAL AND EXTERNAL SPEEDS
- 5.0MHz COUNTING RATE
- INCREMENTED ON POSITIVE TRANSITION OF CLOCK OR NEGATIVE TRANSITION OF CLOCK INHIBIT
- ASYNCHRONOUS PRESET ENABLE



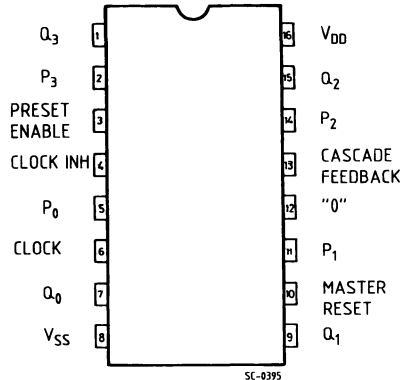
DESCRIPTION

The HCC4522B and HCF4522B are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages and plastic micro packages.

The HCC4522B and HCF4522B are programmable, BCD down counters with a decoded "0" state output for divide-by-N applications. The counters are cascadable. In single stage applications the "0" output is applied to the Preset Enable input. The cascade feedback input allows cascade divide-by-N operation with no additional gates required. The clock Inhibit input allows disabling of the pulse counting function.

Applications for these programmable divide-by-N counters include frequency synthesizers, phase-locked loops and other frequency dividing circuits where low power and/or high noise immunity is required.

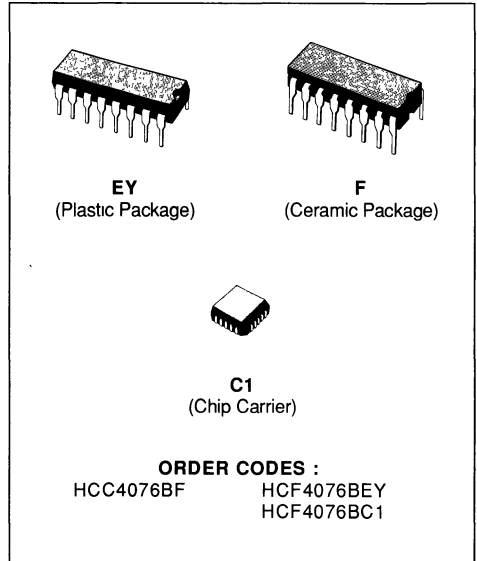
PIN CONNECTION (top view)





BCD RATE MULTIPLEXER

- CASCADABLE IN MULTIPLES OF 4-BITS
- SET TO 9 INPUT AND 9 DETECT OUTPUT
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES "

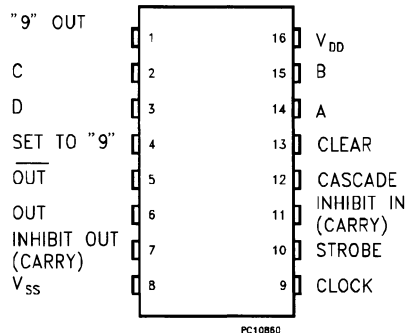


DESCRIPTION

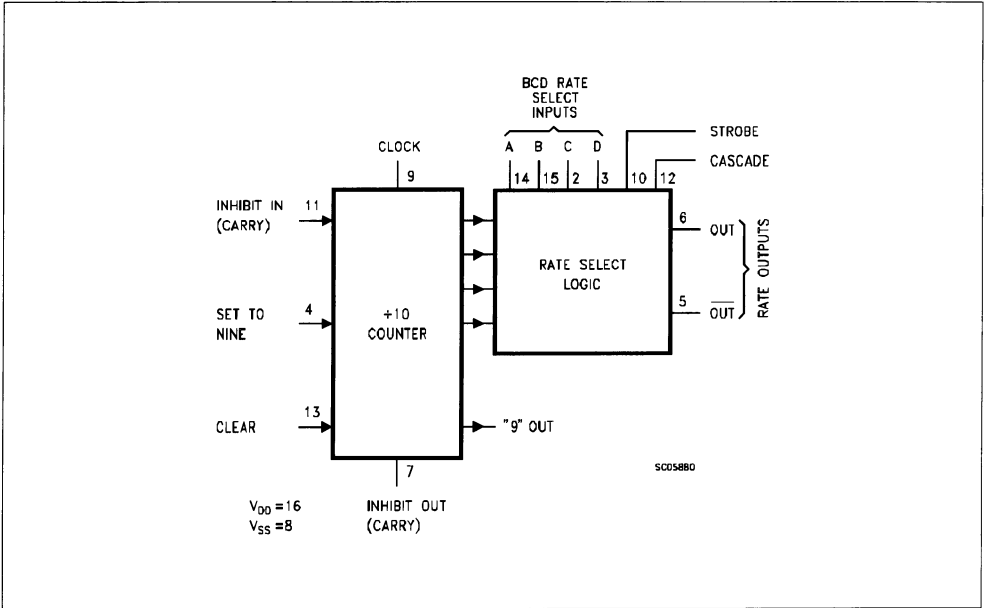
The **HCC4527B** (extended temperature range) and **HCF4527B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in line plastic or ceramic package.

The **HCC/HCF4527B** is a low power 4 bit digital rate multiplier that provides an output pulse rate which is the clock input pulse rate multiplied by 1/10 times the BCD input. For example, when the BCD input is 8, there will be 8 output pulses for every 10 input pulses. This device may be used to preform arithmetic operations (add, subtract, divide, raise to a power), solve algebraic and differential equations, generate natural logarithms and trigonometric functions, A/D and D/A conversion, and frequency division.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

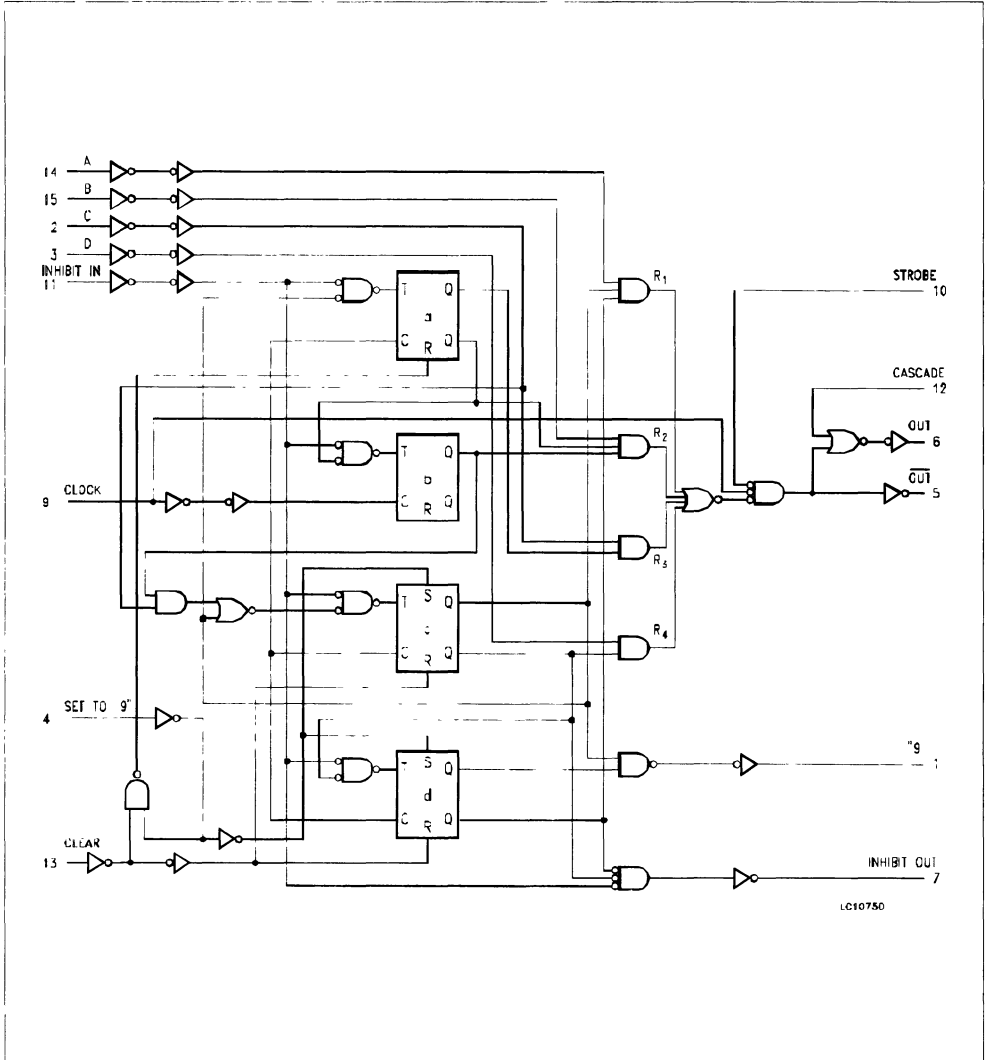
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

LOGIC DIAGRAM



TRUTH TABLE

Inputs										Outputs			
Number of Pulsed or Logic Level (0 = Low; 1 = High; X = Don't Care)										Number of Pulses or Output Logic Level (L = LOW, H = High)			
D	C	B	A	CLK	INH IN	STR	CAS	CLR	SET	OUT	$\overline{\text{OUT}}$	INH OUT	"9" OUT
0	0	0	0	10	0	0	0	0	0	L	H	1	1
0	0	0	1	10	0	0	0	0	0	1	1	1	1
0	0	1	0	10	0	0	0	0	0	2	2	1	1
0	0	1	1	10	0	0	0	0	0	3	3	1	1
0	1	0	0	10	0	0	0	0	0	4	4	1	1
0	1	0	1	10	0	0	0	0	0	5	5	1	1
0	1	1	0	10	0	0	0	0	0	6	6	1	1
0	1	1	1	10	0	0	0	0	0	7	7	1	1
1	0	0	0	10	0	0	0	0	0	8	8	1	1
1	0	0	1	10	0	0	0	0	0	9	9	1	1
1	0	1	0	10	0	0	0	0	0	8	8	1	1
1	0	1	1	10	0	0	0	0	0	9	9	1	1
1	1	0	0	10	0	0	0	0	0	8	8	1	1
1	1	0	1	10	0	0	0	0	0	9	9	1	1
1	1	1	0	10	0	0	0	0	0	8	8	1	1
1	1	1	1	10	0	0	0	0	0	9	9	1	1
X	X	X	X	10	1	0	0	0	0	■	■	H	■
X	X	X	X	10	0	1	0	0	0	L	H	1	1
X	X	X	X	10	0	0	1	0	0	H	●	1	1
1	X	X	X	10	0	0	0	1	0	10	10	H	L
0	X	X	X	10	0	0	0	1	0	L	H	H	L
X	X	X	X	10	0	0	0	0	1	L	H	L	H

● Output same as the first 16 lines of this truth table (depending on value of A, B, C, D)

■ Depends on internal state of counter

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5			5	0.04	5		150	μ A
			0/10			10			10	0.04	10		300	
			0/15			15			20	0.04	20		600	
			0/20			20			100	0.08	100		3000	
		HCF Types	0/5			5			20	0.04	20		150	
			0/10			10			40	0.04	40		300	
			0/15			15			80	0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.53		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	0/18			18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		0/15		Any Input	15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	μ A	
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF deviceThe Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time Clock to Output)		5		110	220	ns
			10		55	110	
			15		45	90	
t_{PLH} t_{PHL}	Propagation Delay Time Clock or Strobe to Output		5		150	300	ns
			10		75	150	
			15		60	120	
t_{PLH}	Propagation Delay Time Clock to Inhibit Output		5		320	640	ns
			10		145	290	
			15		100	200	
t_{PHL}	Propagation Delay Time Clock to Inhibit Output		5		250	500	ns
			10		100	200	
			15		75	150	
t_{PLH} t_{PHL}	Propagation Delay Time Clear to Output		5		380	760	ns
			10		175	550	
			15		130	260	
t_{PLH} t_{PHL}	Propagation Delay Time Clock to "9" or "1" Q Output		5		300	600	ns
			10		125	250	
			15		90	180	
t_{PLH} t_{PHL}	Propagation Delay Time Cascade to Output		5		90	180	ns
			10		45	90	
			15		35	70	
t_{PLH} t_{PHL}	Propagation Delay Time Inhibit Input to Inhibit Output		5		130	260	ns
			10		60	120	
			15		45	90	
t_{PLH} t_{PHL}	Propagation Delay Time Set to Output		5		330	660	ns
			10		150	300	
			15		110	220	
t_{THL} t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_{CL}	Maximum Clock Frequency		5	1.2	2.4		MHz
			10	2.5	5		
			15	3.5	7		
t_w	Clock Pulse Width		5	330	165		ns
			10	170	85		
			15	100	50		
t_r , t_f	Clock Rise or Fall Time		5			15	μs
			10			15	
			15			15	
t_w	Set or Clear Pulse Width		5	160	80		ns
			10	90	45		
			15	60	30		
t_{setup}	Inhibit Input Setup Time		5	100	50		ns
			10	40	20		
			15	20	10		

DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _R	Inhibit Input Removal Time		5	240	120		ns
			10	130	65		
			15	110	55		
t _R	Set Removal Time		5	150	75		ns
			10	80	40		
			15	50	25		
t _R	Clear Removal Time		5	60	30		ns
			10	40	20		
			15	30	15		

APPLICATION NOTE

For fractional multipliers with more than one digit, HCC/HCF4527B devices may be cascaded in two different modes: the Add mode and the Multiply mode (see figures 1 and 2).

When two units are cascaded in Add mode and programmed to 9 and 4 respectively, the more significant unit will have 9 output pulses for every 10 input pulses and the other unit will have 4 output pulses for every 100 input pulses for a total of:

$$\frac{9}{10} + \frac{4}{100} = \frac{94}{100}$$

In the multiply mode, the fraction programmed into

the first rate multiplier is multiplied by the fraction programmed into the second one:

If N₁ = 9 and N₂ = 4

$$f_{out2} = \frac{4}{10} f_{out1}$$

$$f_{out1} = \frac{9}{10} f_{clock}$$

$$f_{out2} = \frac{4}{10} \times \left(\frac{9}{10} f_{clock} \right) = \frac{36}{100} f_{clock}$$

Therefore 36 output pulses for every 100 clock input pulses.

Fig. 1: Two HCC/HCF4527B Cascaded in The "Add" Mode With a Preset Number

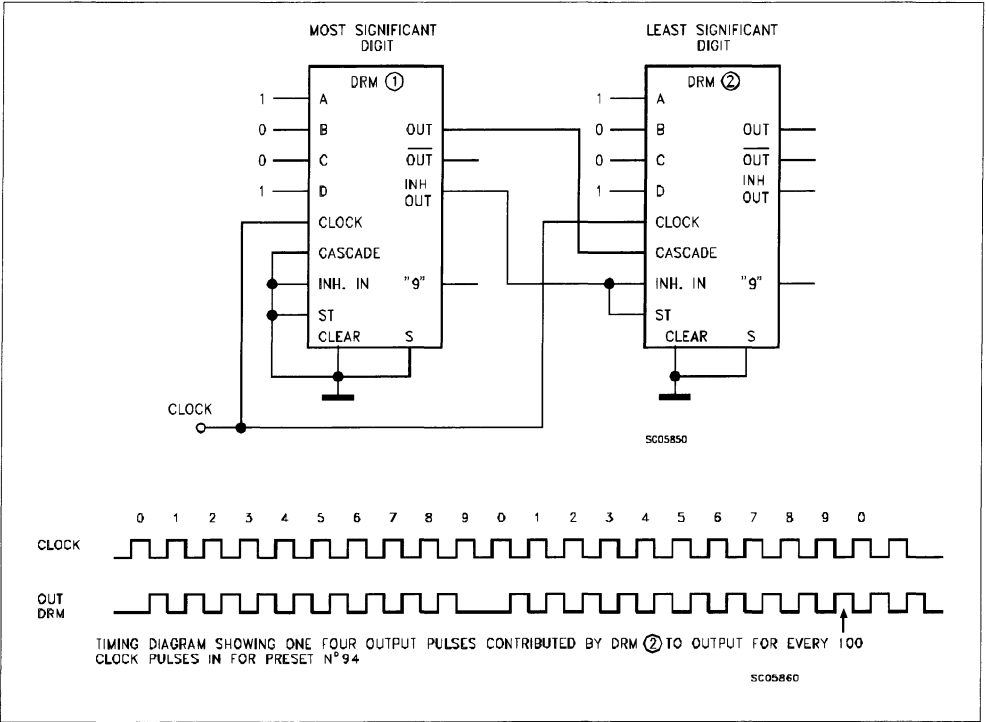


Fig. 2: Two HCC/HCF4527B Cascaded in The "Multiply" Mode With a Preset Number

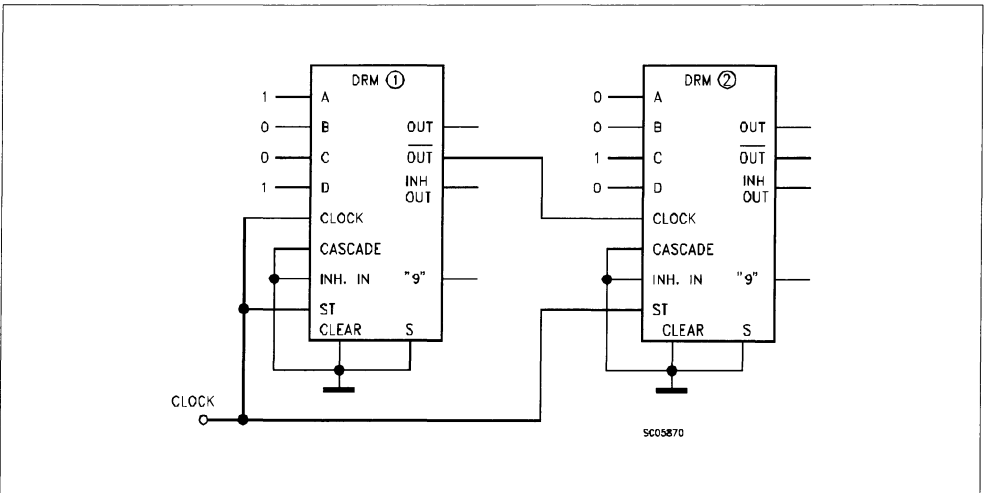
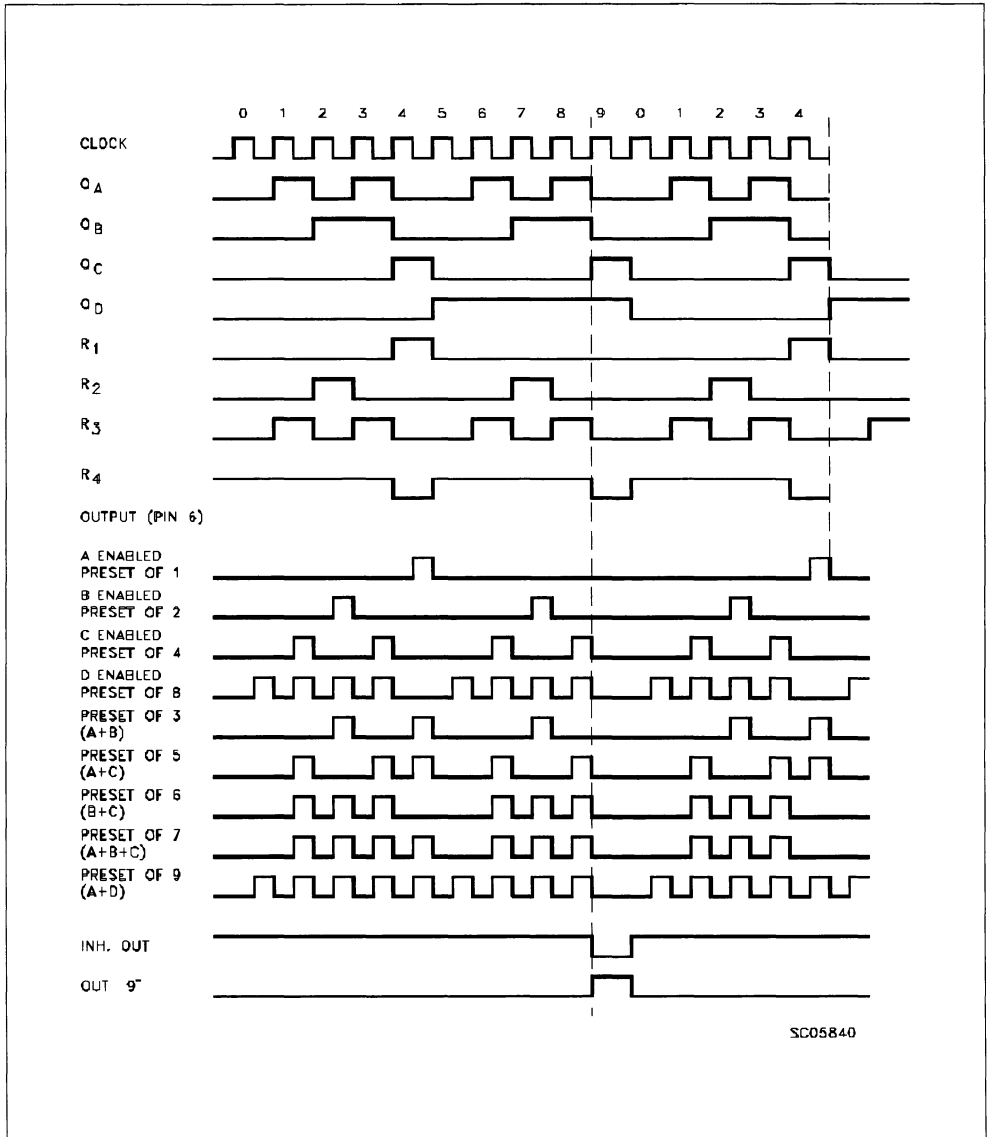
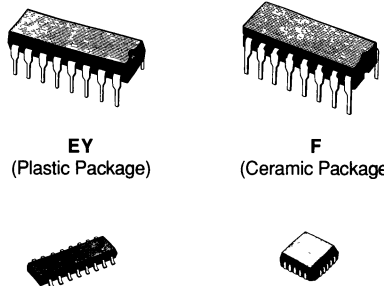


Fig. 3: Timing Diagram (see Logic Diagram)



**DUAL 4-CHANNEL OR SINGLE 8-CHANNEL
ANALOG DATA SELECTOR**

- DATA PATHS ARE BIDIRECTIONAL
- 10 MHz OPERATION (typical)
- 3-STATE OUTPUTS
- "ON" RESISTANCE 125 W TYPICAL @ 15V
- SUPPLY VOLTAGE RANGE = 3Vdc TO 18Vdc



EY
(Plastic Package)

F
(Ceramic Package)

M1
(Micro Package)

C1
(Chip Carrier)

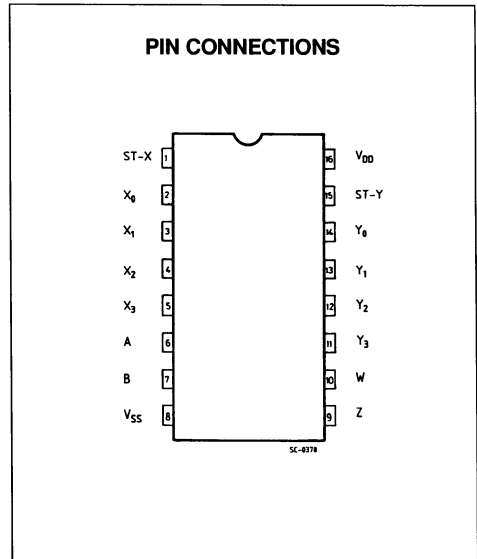
ORDER CODES :
HCC4529BF HCF4529BM1
HCF4529BEY HCF4529BC1

DESCRIPTION

The HCC4529B (extended temperature range) and HCF4529b (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in line plastic or ceramic package and plastic micropackage.

The HCC/HCF4529b is a DUAL 4-CHANNEL or 8-CHANNEL device. One of the two possible functions can be selected by a proper input coding. For the single 8-bit mode Z and W output must be tied together.

HCC/HCF4529B is suitable for digital as well as analogue applications, including 1 of 4 and 1 of 8 data selector functions. Dual binary to 1 of 4 or single binary to 1 of 8 decoder applications can be implemented because the device allow analogue and bidirectional operation.



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

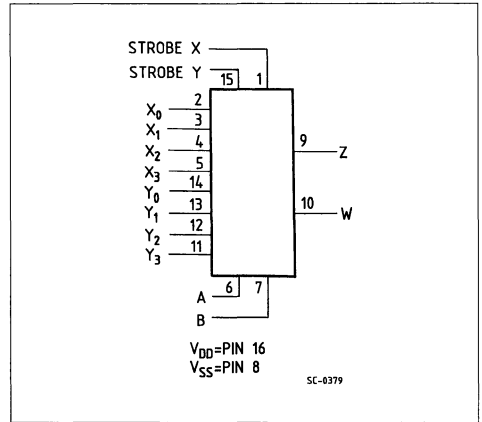
* All voltage values are referred to V_{SS} pin voltage

TRUTH TABLE

ST _X	ST _Y	B	A	Z	W	MODE	
1	1	0	0	X0	Y0	Dual 4-Channel Mode 2 Outputs	
1	1	0	1	X1	Y1		
1	1	1	0	X2	Y2		
1	1	1	1	X3	Y3		
1	0	0	0	X0		Single 8-Channel Mode 1 Output (Z and W tied together)	
1	0	0	1	X1			
1	0	1	0	X2			
1	0	1	1	X3			
0	1	0	0	Y0			
0	1	0	1	Y1			
0	1	1	0	Y2			
0	1	1	1	Y3			
0	0	X	X				High Impedance

X = Don't care

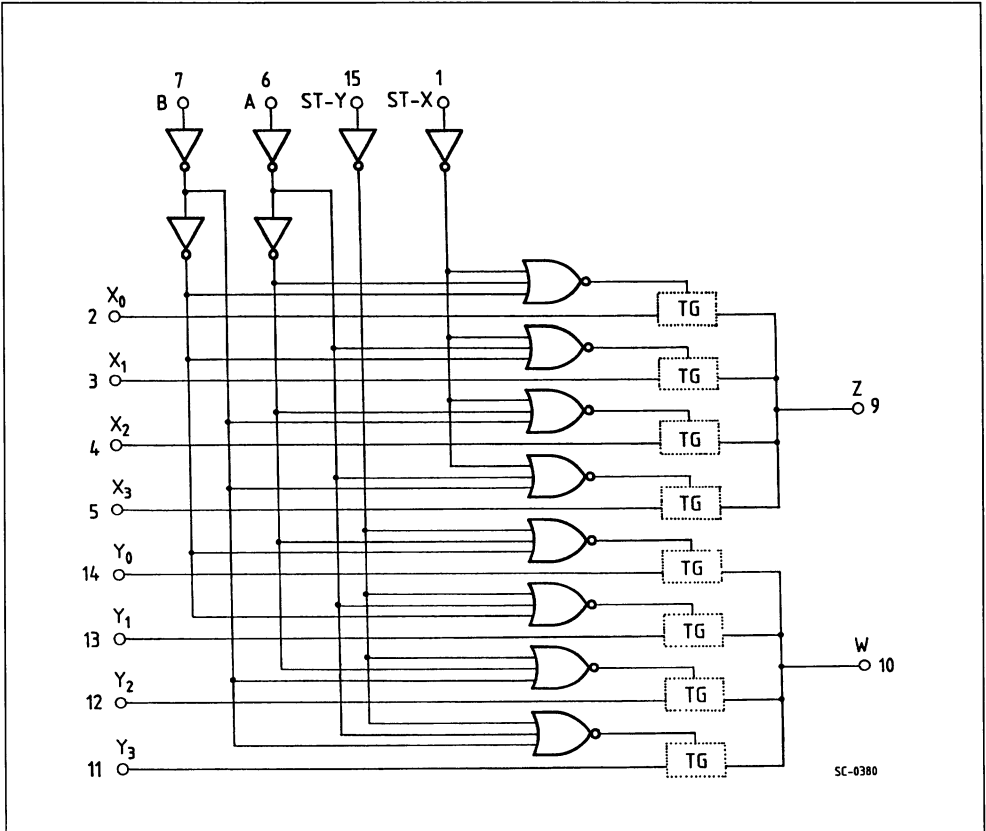
FUNCTIONAL DIAGRAM



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

BLOCK DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions			Value						Unit						
			V _{IS} (V)	V _{SS} (V)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *							
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.					
I _L	Quiescent Current	HCC Types			5		5	0.04	5		150	µA						
					10		10	0.04	10	300								
					15		20	0.04	20	600								
					20		100	0.08	100	3000								
		HCF Types			5		20	0.04	20	150								
					10		40	0.04	40	300								
							0.04	80			600							
SWITCH																		
ON	Resistance	HCC Types	0 ≤ V _I ≤ V _{DD}	0	5		880	470	1050		1200	Ω						
					10		310	180	400	580								
					15		220	125	280	400								
		HCC Types			0 ≤ V _I ≤ V _{DD}	0	5		880	470	1050		1200					
							10		330	180	400		520					
							15		230	125	280		360					
ΔON	Resistance ΔR _{ON} (Between any 2 channels)			0			5			10			Ω					
							10			10								
							15			5								
OFF Channel Leakage Current	Any Channel OFF	HCC Types		0	18	100	±0.1	100		1000	nA							
												All Channel OFF (common OUT/IN)	HCC Types	0	18	100	±0.1	100
	Any Channel OFF	HCC Types																
												All Channel OFF (common OUT/IN)	HCC Types	0	15	300	±0.1	300
CONTROL (Address or Inhibit)																		
V _{IL}	Input Low Voltage		= V _{DD} thru 1KΩ	R _L =1KΩ to V _{SS} I _{IS} < 2µA (On All OFF Channels)	5		1.5		1.5		1.5	V						
					10		3		3		3							
					15		4		4		4							
V _{IH}	Input High Voltage				5	3.5	3.5			3.5	V							
					10	7	7			7								
					15	11	11			11								
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	V _I = 0/18V	18	±0.1		±10 ⁻³	±0.1		±1	µA							
		HCF Types										V _I = 0/15V	15	±0.3	±10 ⁻³	±0.3	±1	
C _i	Input Capacitance		Any Input				5	7.5			pF							

* T_{LOW} = -55 °C for HCC device -40 °C for HCF device

* T_{HIGH} = +125 °C for HCC device +85 °C for HCF device

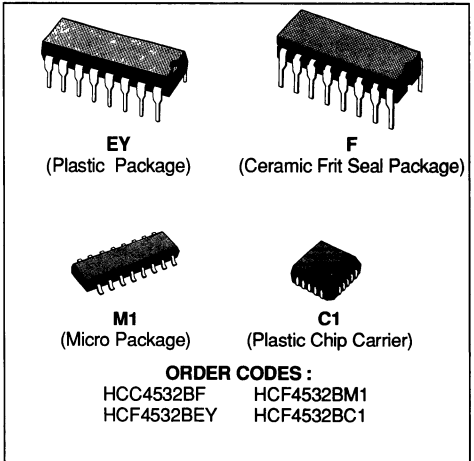
The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5 V, 2 V min with V_{DD} = 10 V, 2.5 V min with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{SS} (V)	V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	V_{in} to V_{out} Propagation Delay Time ($C_L = 50\text{ pF}$, $R_L = 1\text{ K}\Omega$)	0	5 10 15	20 10 8	40 20 15		ns
t_{PLH} t_{PHL}	Propagation Delay Time, Control to Output, $V_{in} = V_{DD}$ or V_{SS} ($V_{in} \leq 10\text{ Vdc}$, $C_L = 50\text{ pF}$, $R_L = 1\text{ K}\Omega$)	0	5 10 15	200 80 50	400 160 120		ns
	Crosstalk, Control to Output ($C_L = 50\text{ pF}$, $R_L = 1\text{ K}\Omega$, $R_{out} = 10\text{ K}\Omega$)	0	5 10 15	5 5 5			mV
	Maximum Control Input Pulse Frequency ($C_L = 50\text{ pF}$, $R_L = 1\text{ K}\Omega$)	0	5 10 15	5 10 12			MHz
	Sine Wave (Distortion) ($V_{in} = 1.77\text{ Vdc RMS}$ Centred @ 0.0 Vdc , $R_L = 10\text{ K}\Omega$, $f = 1\text{ KHz}$)	-5	5	0.36			%
BW	Bandwidth (-3 dB) ($V_{in} = 1.77\text{ Vdc RMS}$ Centred @ 0.0 Vdc) ($R_L = 1\text{ K}\Omega$) ($R_L = 10\text{ K}\Omega$) ($R_L = 100\text{ K}\Omega$) ($R_L = 1\text{ M}\Omega$)	-5	5		35 28 27 26		MHz
	Feedthrough and Crosstalk $\left(20 \text{ Log}_{10} \frac{V_{out}}{V_{in}} = -50 \text{ dB} \right)$ ($R_L = 1\text{ K}\Omega$) ($R_L = 10\text{ K}\Omega$) ($R_L = 100\text{ K}\Omega$) ($R_L = 1\text{ M}\Omega$)	-5	5		850 100 12 1.5		KHz

8-BIT PRIORITY ENCODER

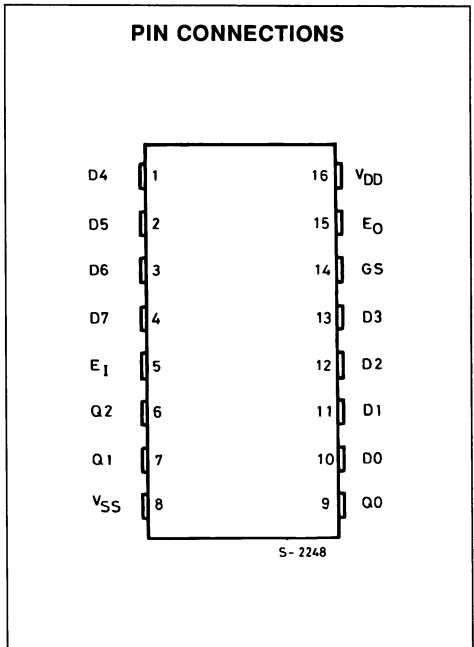
- CONVERTS FROM 1 OF 8 TO BINARY
- PROVIDES CASCADING FEATURE TO HANDLE ANY NUMBER OF INPUTS
- GROUP SELECT INDICATES ONE OR MORE PRIORITY INPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



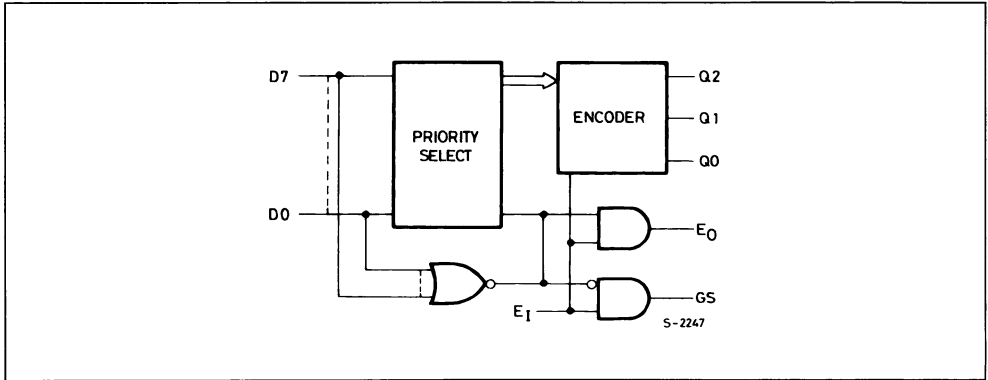
DESCRIPTION

The **HCC4532B** (extended temperature range) and **HCF4532B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF4532** consists of combinational logic that encodes the highest priority input (D7-D0) to a 3-bit binary code. The eight inputs, D7 through D0, each have an assigned priority. D7 is the highest priority and D0 is the lowest. The priority encoder is inhibited when the chip-enable input E_i is low. When E_i is high, the binary representation of the highest-priority input appears on output lines Q2-Q0, and the group select line GS is high to indicate that priority inputs are present. The enable-out (E_o) is high when no priority inputs are present. If any one input is high, E_o is low and all cascaded lower-order stages are disabled.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

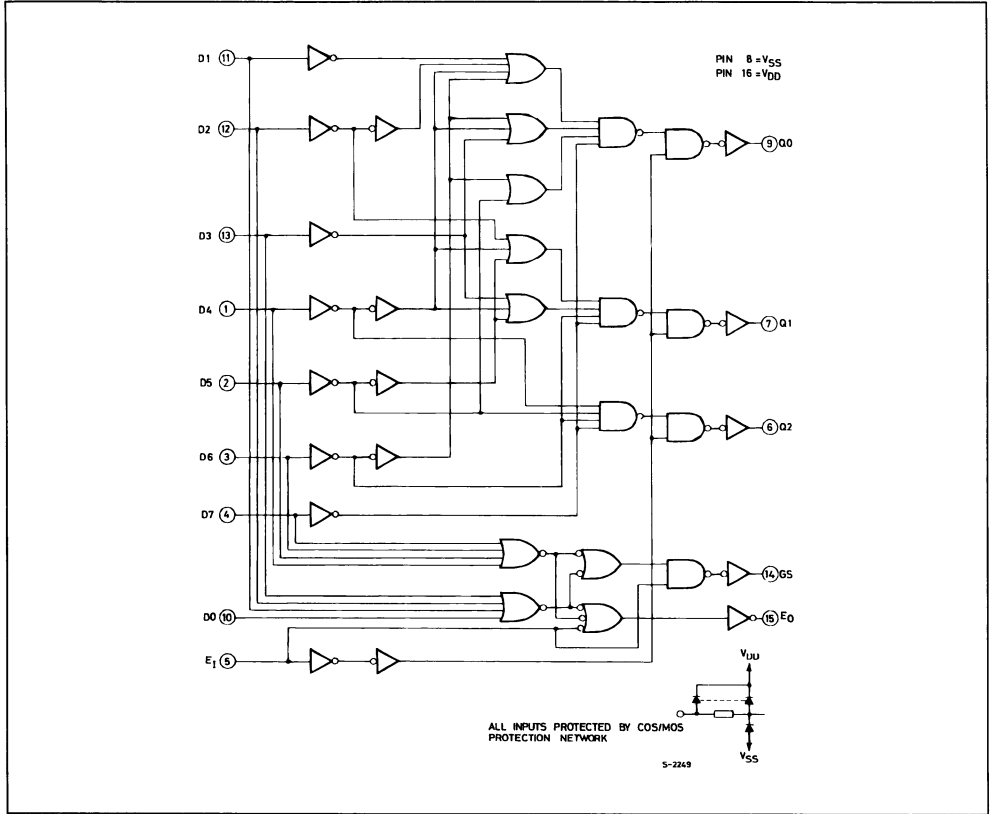
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

Input									Output				
E ₁	D7	D6	D5	D4	D3	D2	D1	D0	GS	Q2	Q1	Q0	E ₀
0	X	X	X	X	X	X	X	X	0	0	0	0	0
1	0	0	0	0	0	0	0	0	0	0	0	0	1
1	1	X	X	X	X	X	X	X	1	1	1	0	0
1	0	1	X	X	X	X	X	X	1	1	1	1	0
1	0	0	1	X	X	X	X	X	1	1	0	0	0
1	0	0	0	1	X	X	X	X	1	1	0	1	0
1	0	0	0	0	1	X	X	X	1	0	1	1	0
1	0	0	0	0	0	1	X	X	1	0	1	0	0
1	0	0	0	0	0	0	1	X	1	0	0	1	0
1	0	0	0	0	0	0	0	1	1	0	0	0	0

X ≡ Don't Care

Logic 1 ≡ High

Logic 0 ≡ Low

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5				3.5		V	
		1/9	< 1	10	7		7				7			
		1.5/13.5	< 1	15	11		11				11			
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5				1.5		1.5	V	
		9/1	< 1	10		3				3		3		
		13.5/1.5	< 1	15		4				4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
		0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15											15
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = -55°C for HCC device : -40°C for HCF device.

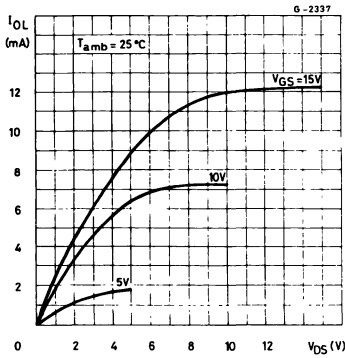
* T_{High} = +125°C for HCC device : +85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

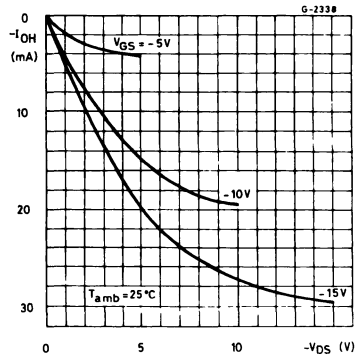
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time (E_1 to E_O , E_1 to GS)		5		110	220	ns
			10		55	110	
			15		45	85	
t_{PLH} , t_{PHL}	Propagation Delay Time (E_1 to Q_m , D_n to GS)		5		170	340	ns
			10		85	170	
			15		65	125	
t_{PLH} , t_{PHL}	Propagation Delay Time (D_n to Q_M)		5		220	440	ns
			10		110	220	
			15		85	160	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

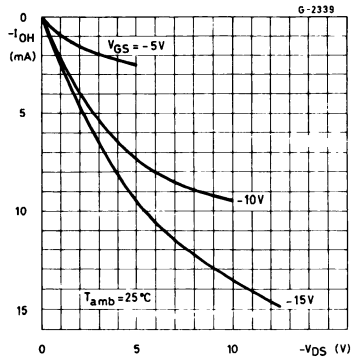
Minimum Output Low (sink) Current Characteristics.



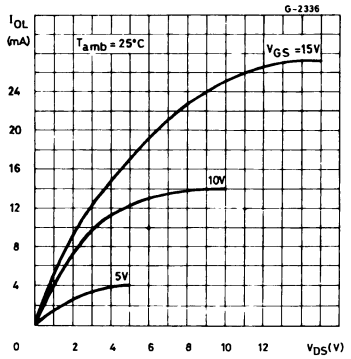
Typical Output High (source) Current Characteristics.



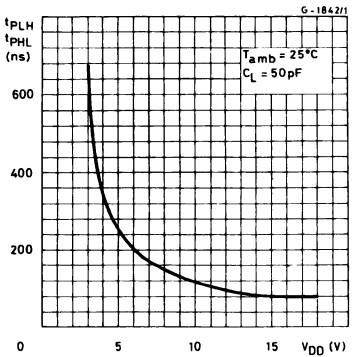
Minimum Output High (source) Current Characteristics.



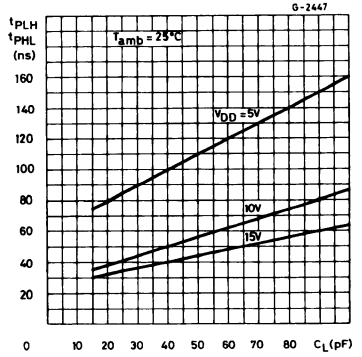
Typical Output Low (sink) Current Characteristics.



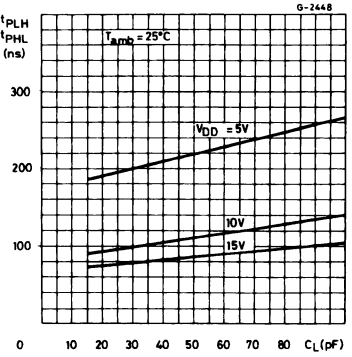
Typical Propagation Delay (Dn to Qm) vs. Supply Voltage.



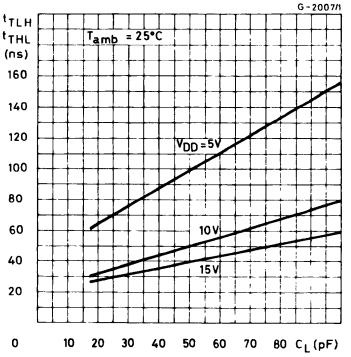
Typical Propagation Delay (E1 to GS, E1 to E0) vs. Load Capacitance.



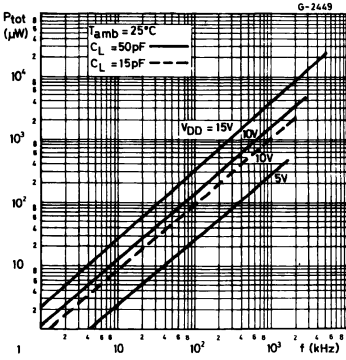
Typical Propagation Delay (Dn to Qm) vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

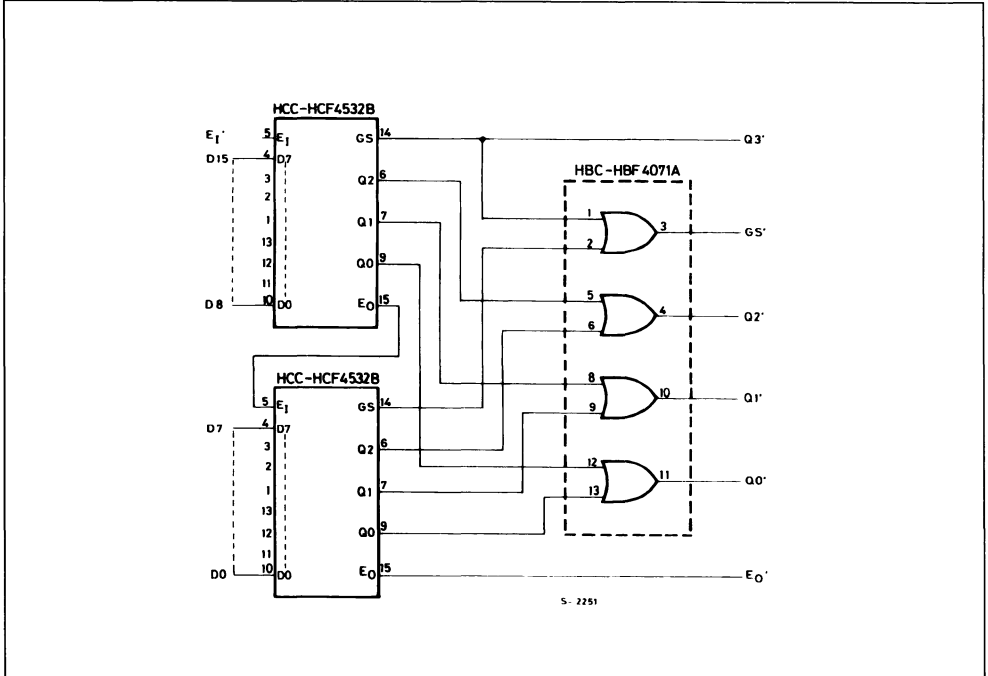


Typical Dynamic Power Dissipation vs. Frequency.



APPLICATIONS

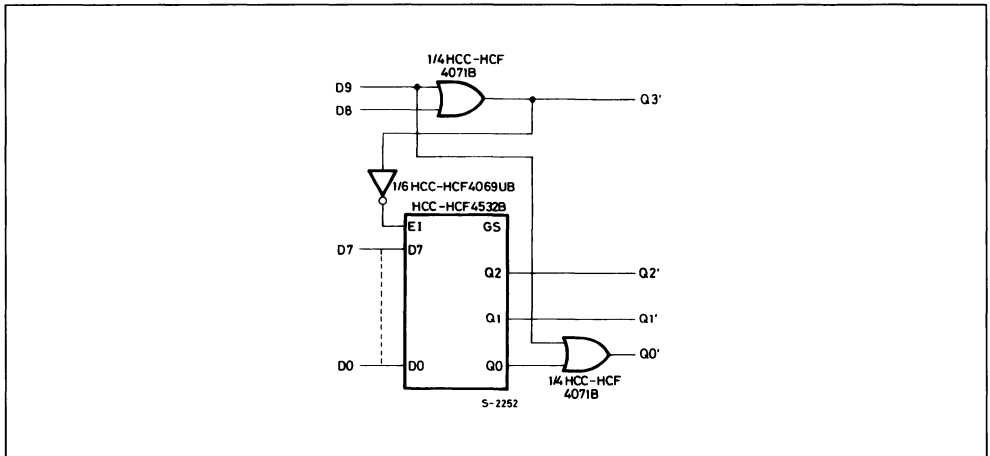
16-LEVEL PRIORITY ENCODER



S-2251

APPLICATIONS (continued)

0-TO-9 KEYBOARD ENCODER



TRUTH TABLE

Input										Output				
D9	D8	D7	D6	D5	D4	D3	D2	D1	D0	GS	Q3'	Q2'	Q1'	Q0
1	X	X	X	X	X	X	X	X	X	0	1	0	0	1
0	1	X	X	X	X	X	X	X	X	0	1	0	0	0
0	0	1	X	X	X	X	X	X	X	1	0	1	1	1
0	0	0	1	X	X	X	X	X	X	1	0	1	1	0
0	0	0	0	1	X	X	X	X	X	1	0	1	0	1
0	0	0	0	0	1	X	X	X	X	1	0	1	0	0
0	0	0	0	0	0	1	X	X	X	1	0	0	1	1
0	0	0	0	0	0	0	1	X	X	1	0	0	1	0
0	0	0	0	0	0	0	0	1	X	1	0	0	0	1
0	0	0	0	0	0	0	0	0	1	1	0	0	0	0

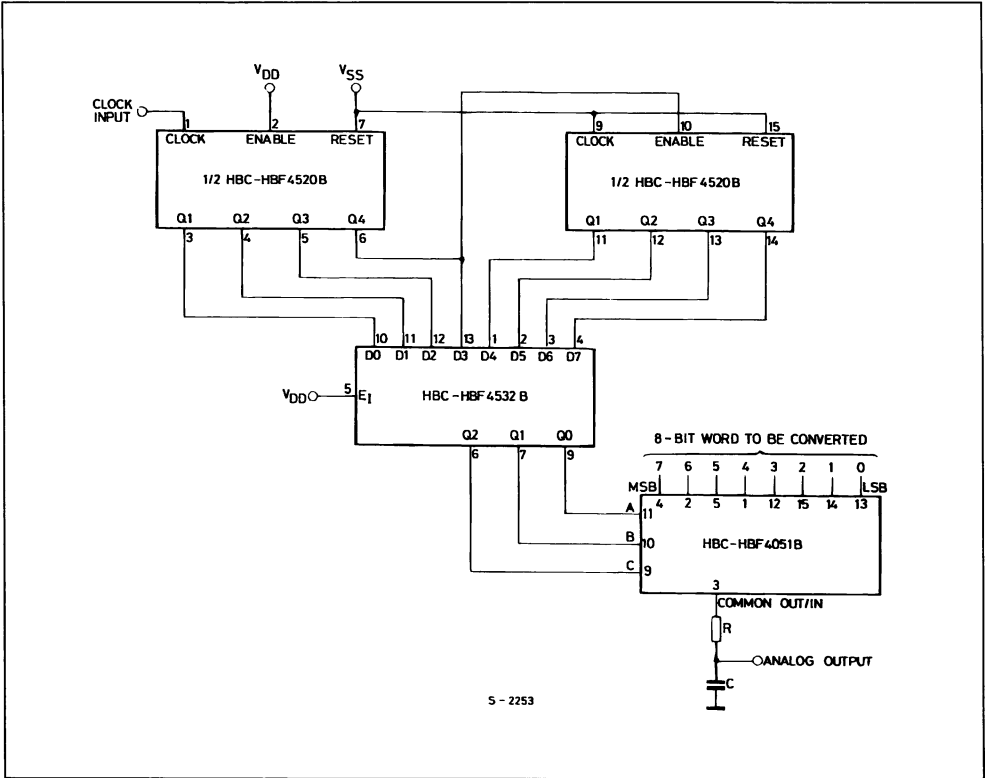
X = Don't Care

Logic 1 ≡ High

Logic 0 ≡ Low

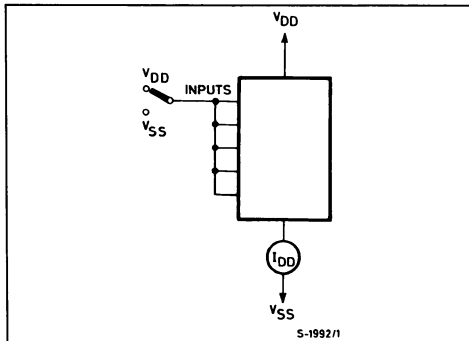
APPLICATIONS (continued)

DIGITAL TO ANALOG CONVERSION

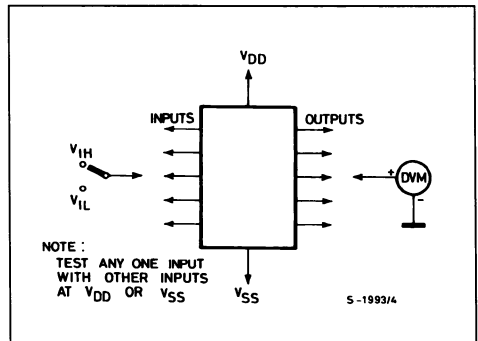


TEST CIRCUITS

Input Leakage Current.

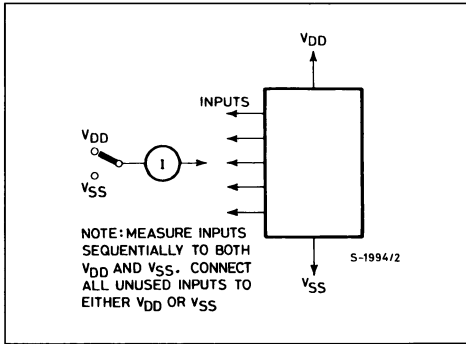


Noise Immunity.

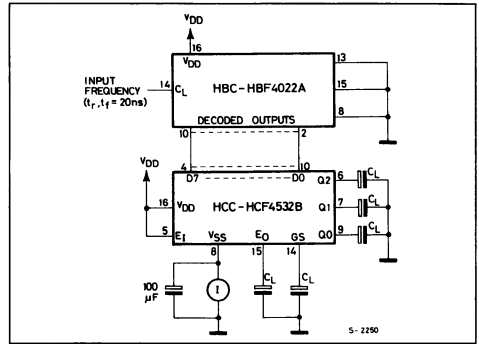


TEST CIRCUITS (continued)

Quiescent Device Current.



Dynamic Power Dissipation.

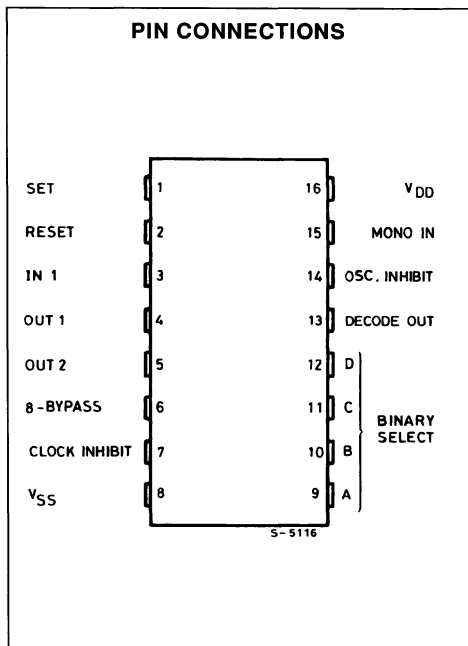
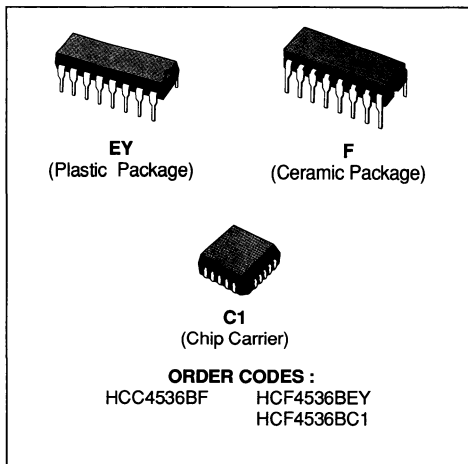


PROGRAMMABLE TIMER

- 24 FLIP-FLOP STAGES - COUNTS FROM 2^0 TO 2^{24}
- LAST 16 STAGES SELECTABLE BY BCD SELECT CODE
- BYPASS INPUT ALLOWS BYPASSING FIRST 8 STAGES
- ON-CHIP RC OSCILLATOR PROVISION
- CLOCK INHIBIT INPUT
- SCHMITT-TRIGGER IN CLOCK LINE PERMITS OPERATION WITH VERY LONG RISE AND FALL TIMES
- ON-CHIP MONOSTABLE OUTPUT PROVISION
- TYPICAL $f_{CL} = 3\text{MHz}$ AT $V_{DD} = 10\text{V}$
- TEST MODE ALLOWS FAST TEST SEQUENCE
- SET AND RESET INPUTS
- CAPABLE OF DRIVING TWO LOW POWER TTL LOADS, ONE LOWER-POWER SCHOTTKY LOAD, OR TWO HTL LOADS OVER THE RATED TEMPERATURE RANGE
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

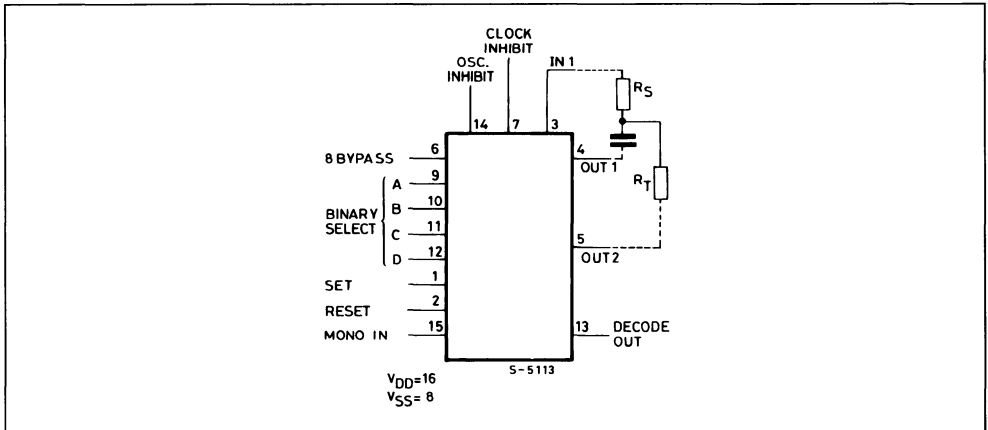
The **HCC4536B** (extended temperature range) and **HCF4536B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The **HCC/HCF4536B** is a programmable timer consisting of 24 ripple-binary counter stages. The salient feature of this device is its flexibility. The device can count from 1 to 2^{24} or the first 8 stages can be bypassed to allow an output, selectable by a 4-bit code, from any one of the remaining 16 stages. It can be driven by an external clock or an RC oscillator that can be constructed using on-chip components. Input IN1 serves as either



the external clock input or the input to the on-chip RC oscillator. OUT1 and OUT2 are connection terminals for the external RC components. In addition, an on-chip monostable circuit is provided to allow a variable pulse width output. Various timing functions can be achieved using combinations of these capabilities. A logic 1 on the 8-BYPASS input enables a bypass of the first 8 stages and makes stage 9 the first counter stage of the last 16 stages. Selection of 1 of 16 outputs is accomplished by the decoder and the BCD inputs A, B, C and D. MONO IN is the timing input for the on-

chip monostable oscillator. Grounding of the MONO IN terminal through a resistor of 10KΩ or higher, disables the one-shot circuit and connects the decoder directly to the DECODE OUT terminal. A resistor to V_{DD} and a capacitor to ground from the MONO IN terminal enables the one-shot circuit and controls its pulse width. A fast test mode is enabled by a logic 1 on 8-BYPASS, SET, and RESET. This mode divides the 24-stage counter into three 8-stage sections to facilitate a fast test sequence.

FUNCTIONAL DIAGRAM



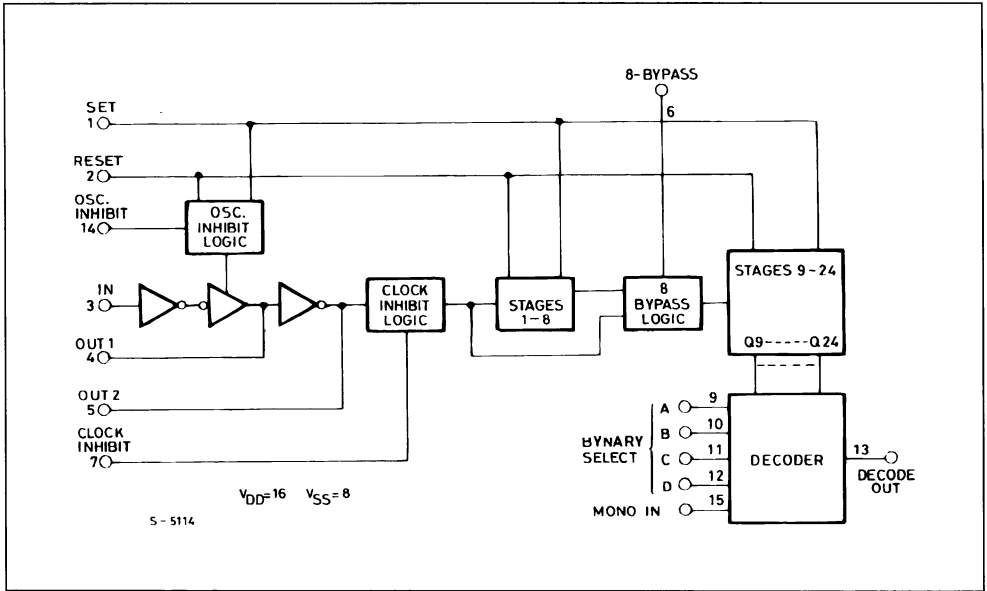
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltages are with respect to V_{SS} (GND).

BLOCK DIAGRAM



TRUTH TABLE

In1	Set	Reset	Clock Inh	Osc Inh	Out1	Out2	Decode Out
⎓	0	0	0	0	⎓	⎓	No Change
⎓	0	0	0	0	⎓	⎓	Advance to Next State
X	1	0	0	0	0	1	1
X	0	1	0	0	0	1	0
X	0	0	1	0			No Change
0	0	0	0	X	0	1	No Change
1	0	0	0	⎓	⎓	⎓	Advance to Next State

0 = Low Level 1 = High Level X = Don't Care

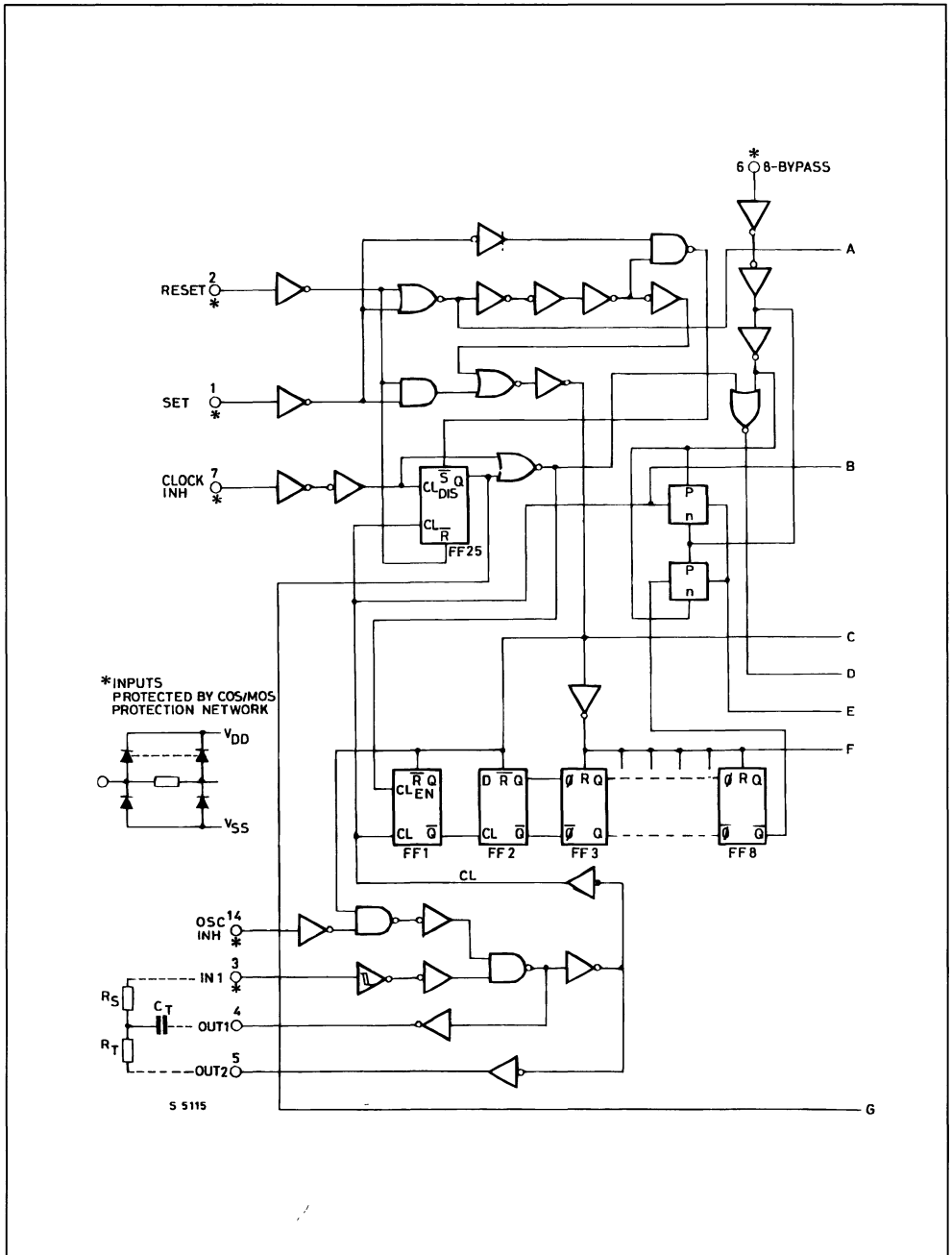
DECODE OUT SELECTION TABLE

D	C	B	A	Number or Stages In Divider Chain	
				8-BYPASS = 0	8-BYPASS = 1
0	0	0	0	9	1
0	0	0	1	10	2
0	0	1	0	11	3
0	0	1	1	12	4
0	1	0	0	13	5
0	1	0	1	14	6
0	1	1	0	15	7
0	1	1	1	16	8
1	0	0	0	17	9
1	0	0	1	18	10
1	0	1	0	19	11
1	0	1	1	20	12
1	1	0	0	21	13
1	1	0	1	22	14
1	1	1	0	23	15
1	1	1	1	24	16

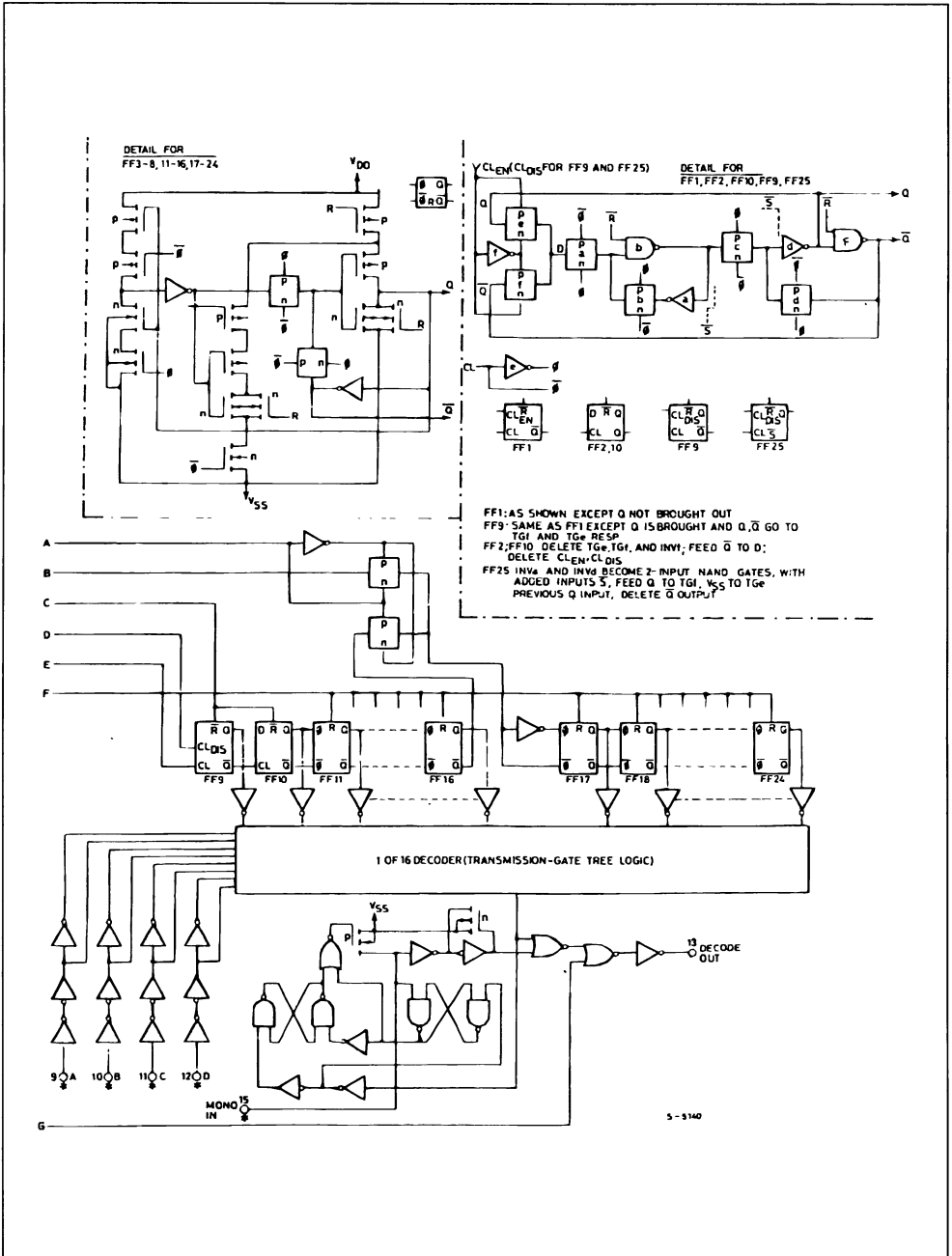
0 = Low Level

1 = High Level

LOGIC DIAGRAMS (continued on next page)



LOGIC DIAGRAMS (continued)



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

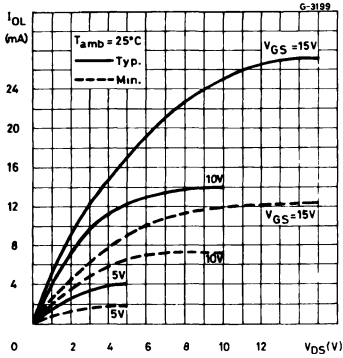
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
0/10	9.5			10	- 1.3		- 1.1	- 2.6		- 0.9				
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1	\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15			15		\pm 0.3	\pm 10 ⁻⁵	\pm 0.3		\pm 1		
C _I	Input Capacitance		Any Input						5	7.5		pF		

* T_{Low} = - 55°C for HCC device . - 40°C for HCF device* T_{High} = + 125°C for HCC device . + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min with V_{DD} = 5V , 2V min with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

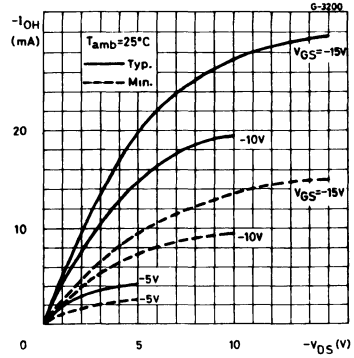
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\% / ^{\circ}\text{C}$ all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)	Min.	Typ.	Max.		
t_{PLH} , t_{PHL}	Propagation Delay Time Clock to Q1, 8-bypass High	5		1	2	μs	
		10		0.5	1		
		15		0.35	0.7		
	Clock to Q1, 8-bypass Low	5		2.5	5	μs	
		10		0.8	0.6		
		15		0.6	1.2		
	Clock to Q16	5		4	8	μs	
		10		1.5	3		
		15		1	2		
Q_n to Q_{n+1}	5		150	300	ns		
	10		75	150			
	15		50	100			
t_{PLH}	Propagation Delay Time	5		300	600	ns	
		10		125	250		
		15		80	160		
t_{PHL}	Reset to Q_n	5		3	6	μs	
		10		1	2		
		15		0.75	1.5		
t_{THL} , t_{TLH}	Transition Time	5		100	200	ns	
		10		50	100		
		15		40	80		
tw	Pulse Widht Clock	5		200	400	ns	
		10		75	150		
		15		50	100		
	Set	5		200	400	ns	
		10		100	200		
		15		60	120		
	Reset	5		3	6	μs	
		10		1	2		
		15		0.75	1.5		
	Recovery Time Set	5		2.5	5	μs	
		10		1	2		
		15		0.6	1.6		
	Reset	5		3.5	7	μs	
		10		1.5	3		
		15		1	2		
t_r , t_f	Clock Input Rise or Fall Time	5	Unlimited			μs	
		10					
		15					
f_{CL}	Maximum Clock Input Frequency	5	0.5	1		MHz	
		10	1.5	3			
		15	2.5	5			

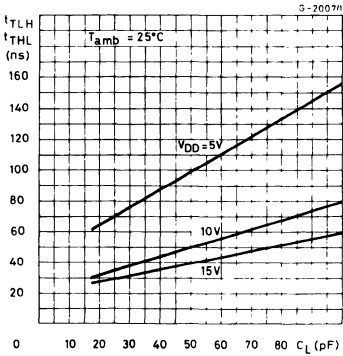
Output Low (sink) Current Characteristics.



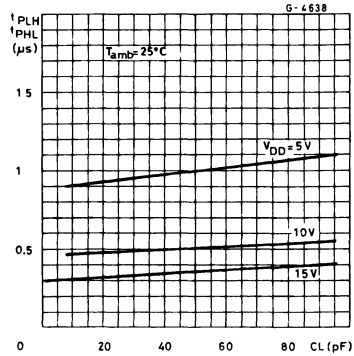
Output High (source) Current Characteristics.



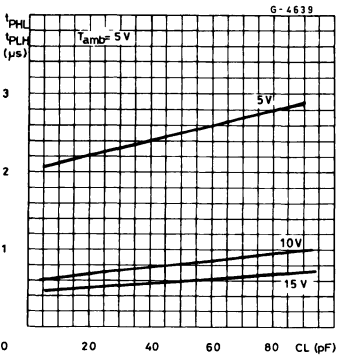
Typical Transition Time vs. Load Capacitance.



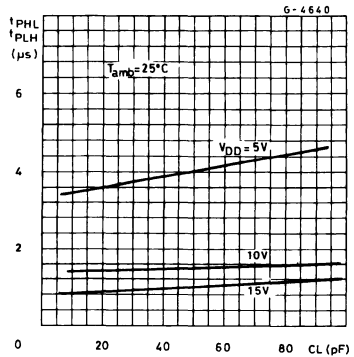
Typical Propagation Delay Time vs. Load Capacitance (clock to Q1, 8 Bypass high).



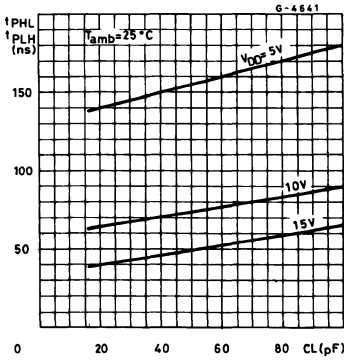
Typical Propagation Delay Time vs. Load Capacitance (Clock to Q1, 8 Bypass low).



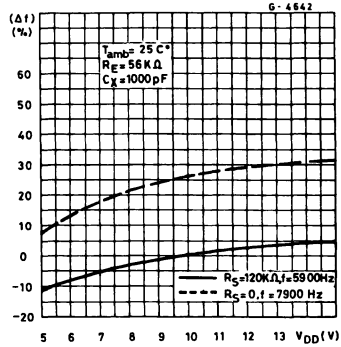
Typical Propagation Delay Time vs. Load Capacitance (Clock to Q16, 8 Bypass high).



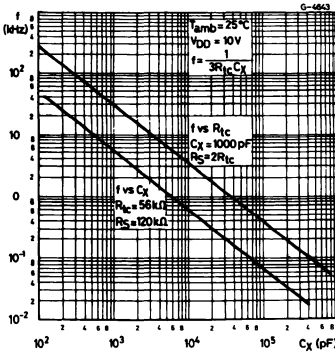
Typical Propagation Delay Time vs. Load Capacitance (Q_N to Q_{N+1}).



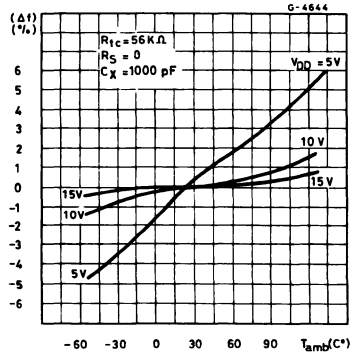
Typical RC Oscillator Frequency Deviation vs. Supply Voltage.



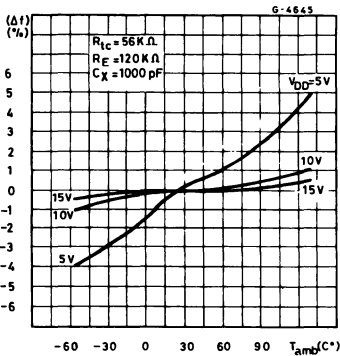
Typical RC Oscillator Frequency Deviation vs. Time Constant Resistance and Capacitance.



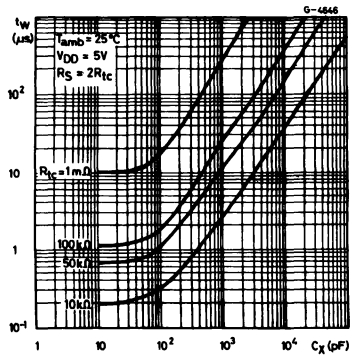
Typical RC Oscillator Frequency Deviation vs. Ambient Temperature ($R_S = 0$).



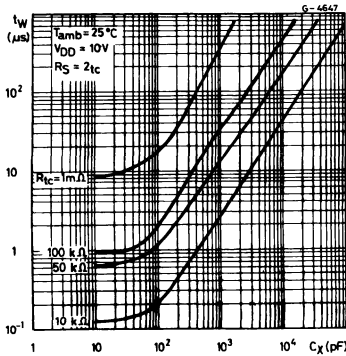
Typical RC Oscillator Frequency Deviation vs. Ambient Temperature ($R_S = 120K\Omega$).



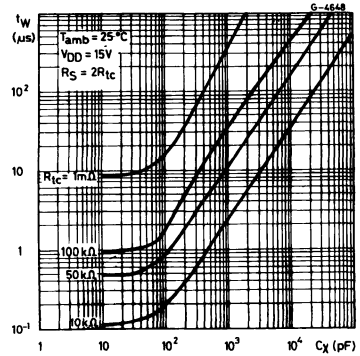
Typical Pulse Width vs. External Capacitance ($V_{DD} = 5V$).



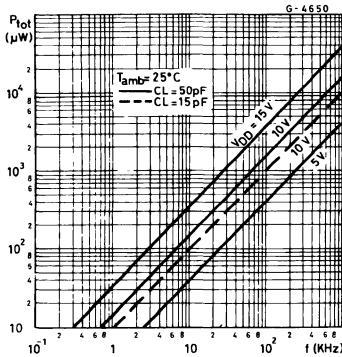
Typical Pulse Width vs. External Capacitance ($V_{DD} = 10V$).



Typical Pulse Width vs. External Capacitance ($V_{DD} = 15V$).

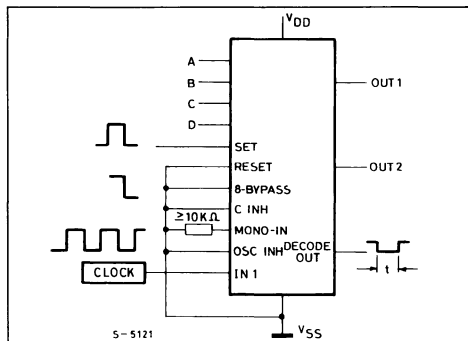


Typical Dynamic Power Dissipation vs. Input Pulse Frequency.

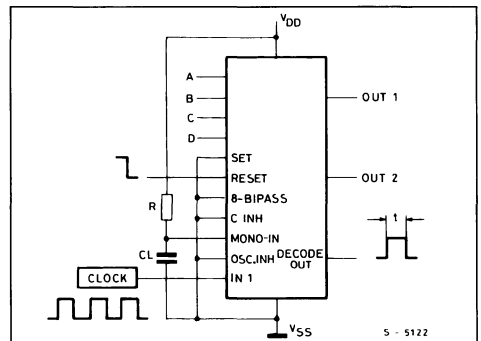


TYPICAL APPLICATIONS

Time Internal Configuration Using External Clock ; Set and Clock Inhibit Functions.

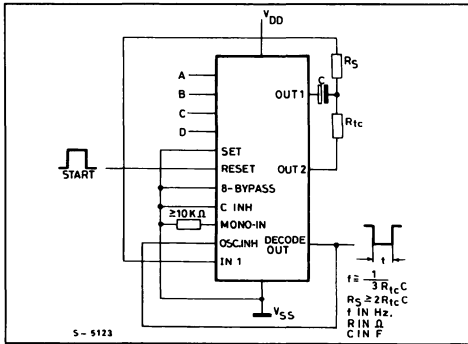


Time Internal Configuration Using External Clock ; Reset and Output Monostable to Achieve a Pulse Output.

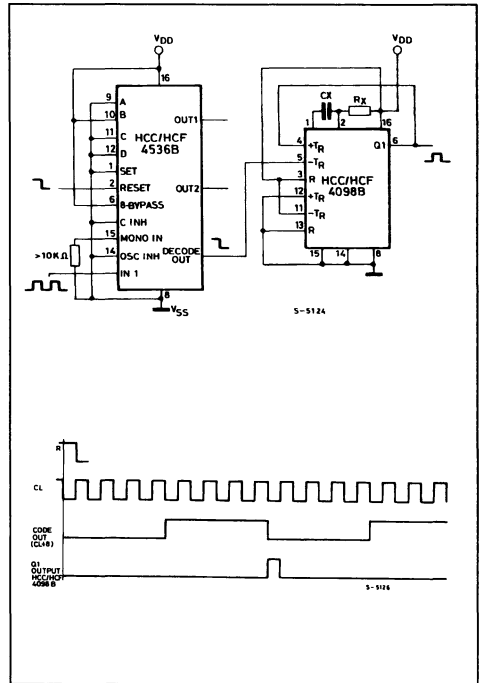


TYPICAL APPLICATIONS (Continued)

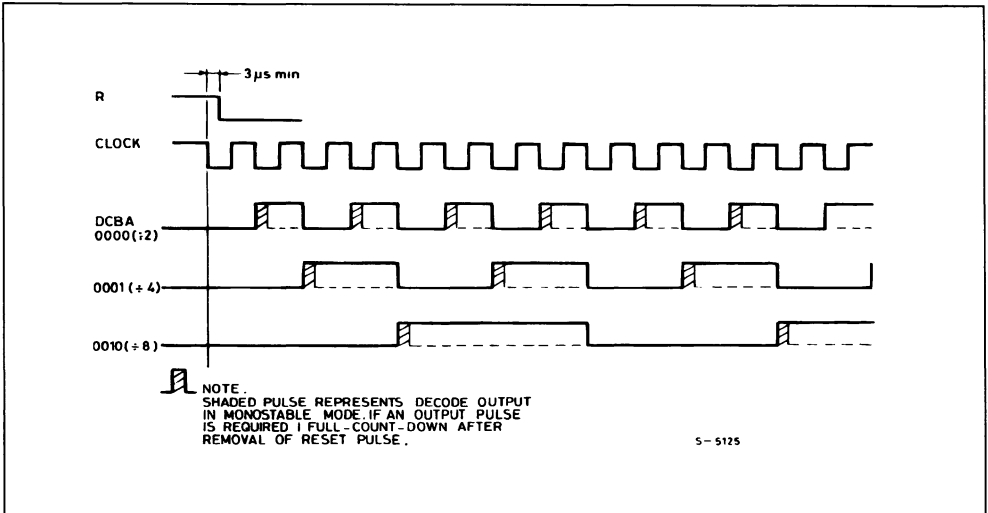
Time Interval Configuration Using Onchip RC Oscillator and Reset Input to Initiate Time Interval.



Application Showing Use of 4098B and 4536B to get Decode Pulse 8 Clock Pulses after Reset Pulse.



TIMING DIAGRAM



Functional Test Sequence					
Inputs				Outputs	Comments
In1	Set	Reset	8-Bypass	Decade Out Q1 Thru Q24	All 24 steps are in reset mode.
1	0	1	1	0	Counter is in three 8-stage section in parallel mode.
1	1	1	1	0	
0	1	1	1	0	First "1" to "0" Transition of Clock
1 0 — —	1	1	1		255 "1" to "0" transitions are clocked in the counter.
0	1	1	1	1	The 255 "1" to "0" Transition
0	0	0	0	1	Counter converted back to 24 stages in series mode. Set and Reset must be connected together and simultaneously go from "1" to "0".
1	0	0	0	1	In ₁ switches to a "1".
0	0	0	0	0	Counter Ripples from an all "1" state to an all "0" state.

FUNCTIONAL TEST SEQUENCE

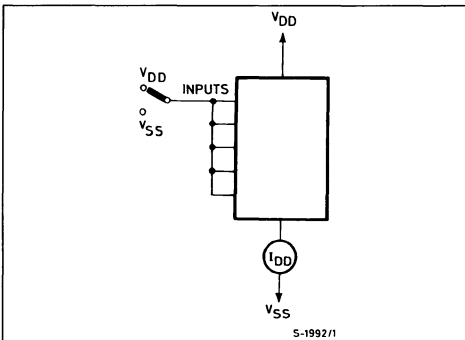
Test Function has been included for the reduction of test time required to exercise all 24 counter stages.

This test function divides the counter into three 8-stage section and 255 counts are loaded in each of the 8-stage sections in parallel. All flip-flops are now

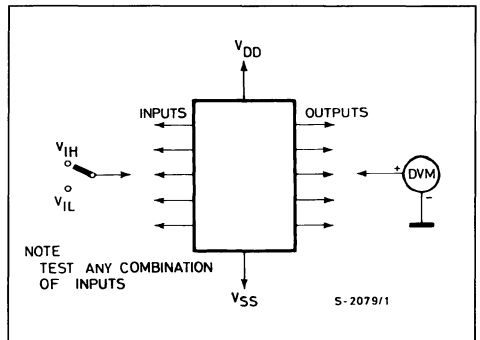
at a "1". The counter is now returned to the normal 24-steps in series configuration. One more pulse is entered into In₁ which will cause the counter to ripple from an all "1" state to an all "0" state.

TEST CIRCUITS

Quiescent Device Current.

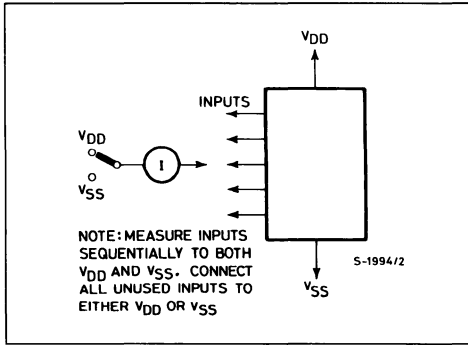


Input Voltage.

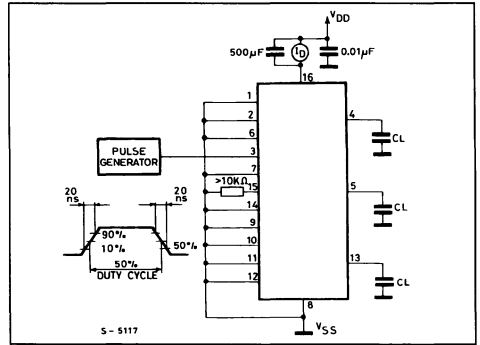


TEST CIRCUITS (continued)

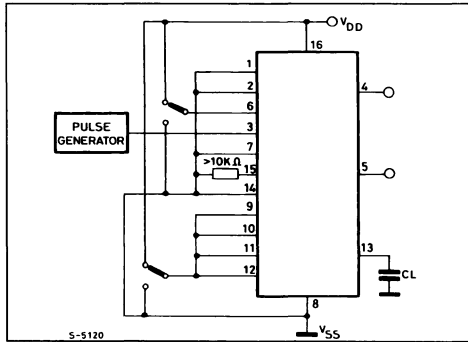
Input Leakage Current.



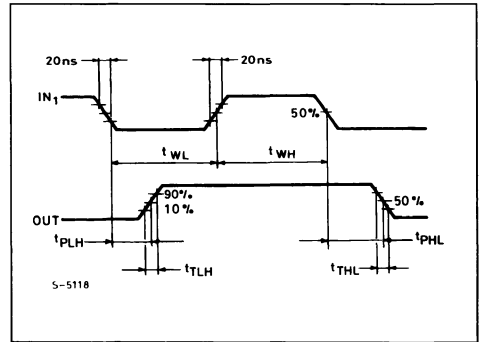
Dynamic Power Dissipation.



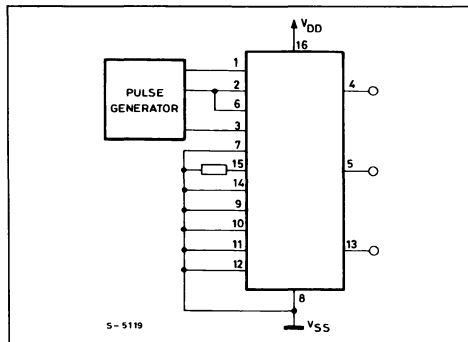
Switching Time.



Input Waveforms for Switching-Time.



Functional.





DUAL MONOSTABLE MULTIVIBRATOR

- RETRIGGERABLE/RESETTABLE CAPABILITY
- TRIGGER AND RESET PROPAGATION DELAYS INDEPENDENT OF R_X , C_X
- TRIGGERING FROM LEADING OR TRAILING EDGE
- Q AND \bar{Q} BUFFERED OUTPUTS AVAILABLE
- SEPARATE RESETS
- WIDE RANGE OF OUTPUT-PULSE WIDTHS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- SCHMITT TRIGGER INPUT ALLOWS UNLIMITER RISE AND FALL TIMES ON + TR AND - TR INPUTS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

EY
(Plastic Package)

F
(Ceramic Package)

M1
(Micro Package)

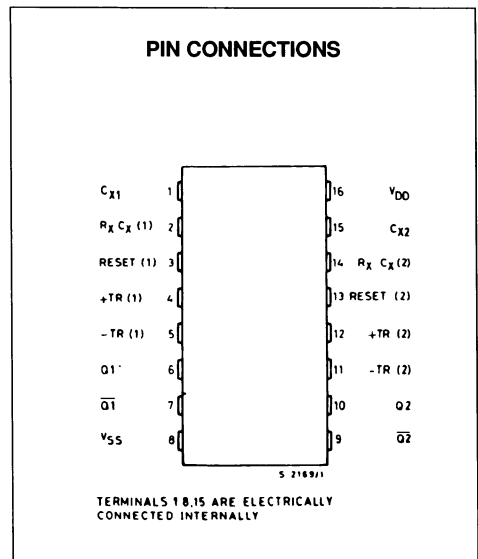
C1
(Chip Carrier)

ORDER CODES :

HCC4538BF	HCF4538BM1
HCF4538BEY	HCF4538BC1

DESCRIPTION

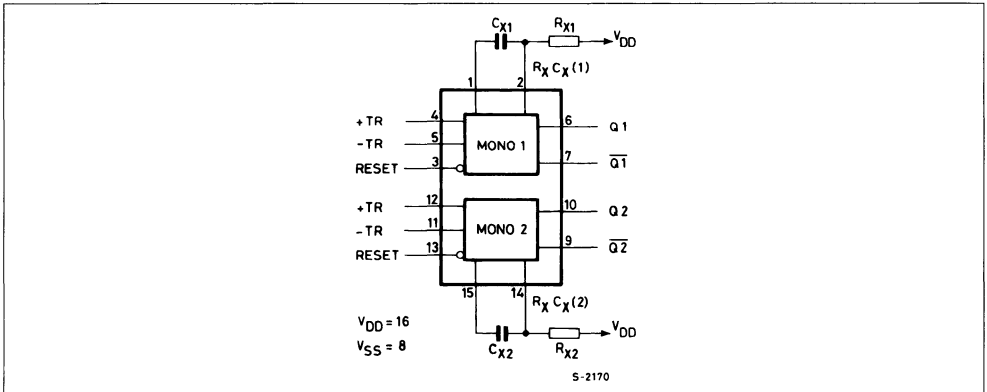
The **HCC4538B** (extended temperature range) and **HCF4538B** (intermediate temperature range) are monolithic integrated circuit, available in 16-lead dual in-line plastic or-ceramic package and plastic micro package. The **HCC/HCF4538B** dual precision monostable multivibrator provides stable retriggerable/resettable one-shot operation for any fixed-voltage timing application. An external resistor (R_X) and an external capacitor (C_X) control the timing and accuracy for the circuit. Adjustment of R_X and C_X provides a wide range of output pulse widths from the Q and \bar{Q} terminals. The time delay from trigger input to output transition (trigger propagation delay) and the time delay from reset input to output transition (reset propagation delay) are independent of R_X and C_X . Precision control of output pulse widths is achieved through linear CMOS techniques. Leading-edge-triggering (+ TR) and trailing-edge-triggering (- TR) inputs are provided for triggering from either edge of an input pulse. An unused + TR input should be tied to V_{SS} . An unused - TR input should be tied to V_{DD} . A RESET (on low level) is provided for immediate termination of the output pulse or to



present output pulses when power is turned on. An unused RESET input should be tied to V_{DD}. However, if an entire section of the HCC/HCF4538B is not used, its inputs must be tied to either V_{DD} or V_{SS} (see table 1). In normal operation the circuit triggers (extends the output pulse one period) on the application of each new trigger pulse. For operation in the non-retriggerable mode, Q̄ is connected to - TR

when leading-edge triggering (+ TR) is used or Q is connected to + TR when trailing-edge triggering (- TR) is used. The time period (T) for this multivibrator can be calculated by: $T = R_X C_X$. The min. value of external resistance, R_x, is 4KΩ. The max. and min. values of external capacitance, C_x, are 100μF and 5nF, respectively.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package Temperature Range	200 100	mW mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C

LOGIC DIAGRAM (1/2 of device shown)

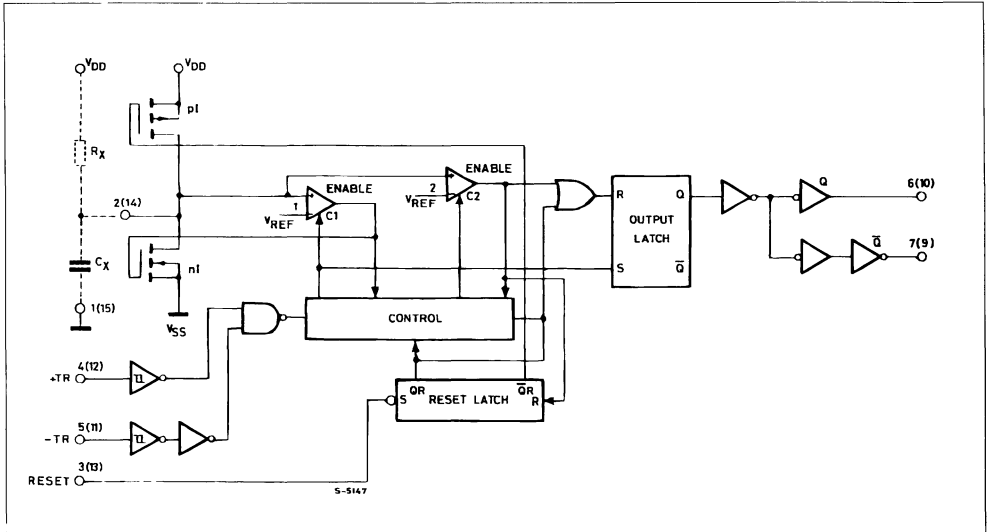
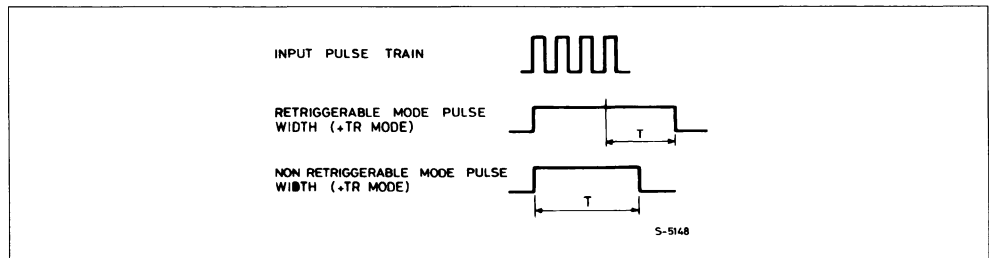


TABLE 1: Functional Terminal Connections

Function	VDD to Term. NO		VSS to Term. NO		Input Pulse to Term. No		Other Connections	
	Mono (1)	Mono (2)	Mono (1)	Mono (2)	Mono (1)	Mono (2)	Mono (1)	Mono (2)
Leading-Edge Trigger/Retriggerable	3, 5	11, 13			4	12		
Leading-Edge Trigger/Non-retriggerable	3	13			4	12	5, 7	11, 9
Trailing-Edge Trigger/Retriggerable	3	13	4	12	5	11		
Trailing-Edge Trigger/Non-retriggerable	3	13			5	11	4, 6	12, 10

- Notes : 1 A Retriggerable one-shot multivibrator has an output pulse width which is extended on full time period (T) after application of the last trigger pulse
 2 A Non-retriggerable one-shot multivibrator has a time period (T) referenced from the application of the first trigger pulse

Pulse Width



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{ol} (μ A)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		5		0.04	5		150	
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95	5		4.95		V	
		0/10		< 1	10	9.95		9.95	10		9.95			
		0/15		< 1	15	14.95		14.95	15		14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.8		-1.6	-3.2		-1.3		
			0/5	4.6		5	-0.61		-0.51	-1		-0.42		
			0/10	9.5		10	-1.5		-1.3	-2.6		-1.1		
0/15	13.5		15	-4		-3.4	-6.8		-2.8					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.61		0.51	1		0.42		
			0/10	0.5		10	1.5		1.3	2.6		1.1		
			0/15	1.5		15	3.6		3.4	6.8		2.8		
I _{IH} , I _{IL}	Input Leakage Current	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{LOW} = -55 °C for HCC device -40 °C for HCF device

* T_{HIGH} = +125 °C for HCC device +85 °C for HCF device

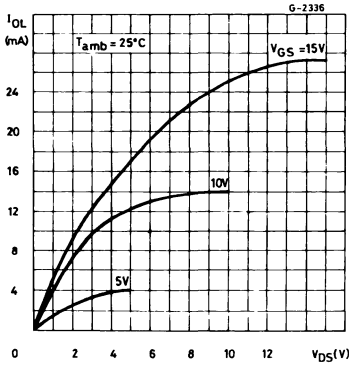
The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5 V, 2 V min with V_{DD} = 10 V, 2.5 V min with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

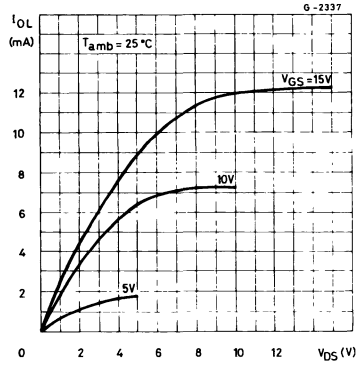
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{PLH} t_{PHL}	Propagation Delay Time +TR or -TR to Q or \bar{Q}		5		300	600	ns
			10		150	300	
			15		100	220	
t_{PLH} t_{PHL}	Propagation Delay Time Reset to Q or \bar{Q}	$R_L = 1\text{ K}\Omega$	5		250	500	ns
			10		125	250	
			15		95	190	
t_{WH} t_{WL}	Minimum Input Pulse Width +TR, -TR or Reset	$R_L = 1\text{ K}\Omega$	5		80	140	ns
			10		40	80	
			15		30	60	
t_{WT}	Output Pulse Width - Q or \bar{Q} ($C_X = 0.005\text{ }\mu\text{F}$, $R_X = 10\text{ K}\Omega$ *)		5	57	60.6	64.5	μs
			10	55	58.9	63.0	
			15	55	59.1	63.5	
t_{WT}	Output Pulse Width - Q or \bar{Q} ($C_X = 0.1\text{ }\mu\text{F}$, $R_X = 100\text{ K}\Omega$)		5	9.4	9.97	10.5	ms
			10	9.4	9.95	10.6	
			15	9.5	10.00	10.6	
t_{WT}	Output Pulse Width - Q or \bar{Q} ($C_X = 10\text{ }\mu\text{F}$, $R_X = 100\text{ K}\Omega$)		5	0.95	1.00	1.06	s
			10	0.95	1.00	1.06	
			15	0.96	1.00	1.07	
t_w	Pulse Width Match Between Circuits in Same Package: $\frac{100(T_1 - T_2)}{T_1}$ ($C_X = 0.1\text{ }\mu\text{F}$, $R_X = 100\text{ K}\Omega$)		5		± 1		%
			10		± 1		
			15		± 1		
t_{rr}	Minimum Retrigger Time		5	0			ns
			10	0			
			15	0			
C_{IN}	Input Capacitance		Any Input		5	7.5	pF

* Minimum R_X value = $4\text{ K}\Omega$, minimum C_X value = 500 pF

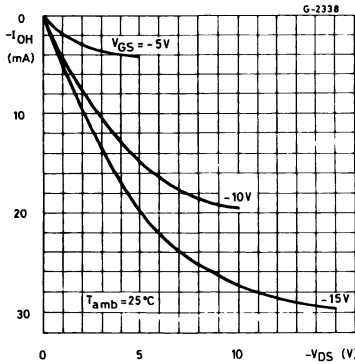
Typical Output Low (sink) Current Characteristics



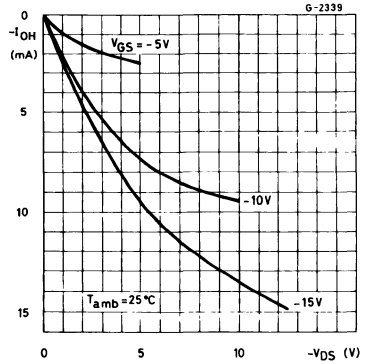
Minimum Output Low (sink) Current Characteristics



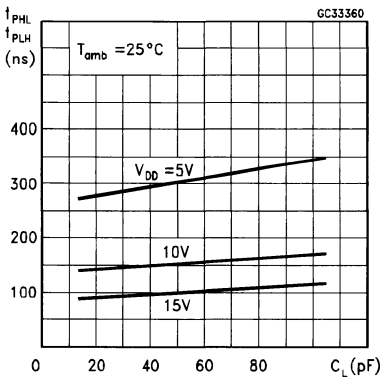
Typical Output High (source) Current Characteristics



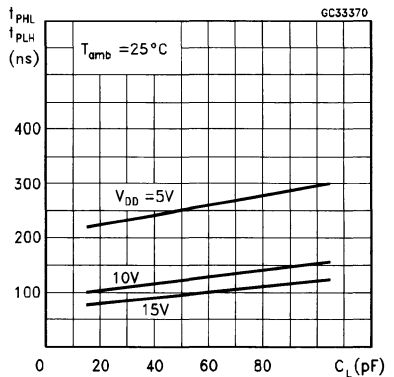
Minimum Output High (source) Current Characteristics



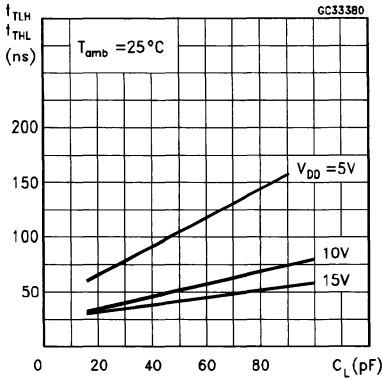
Typical Propagation Delay Time as a Function of Load Capacitance (+TR or -TR to Q or Q̄)



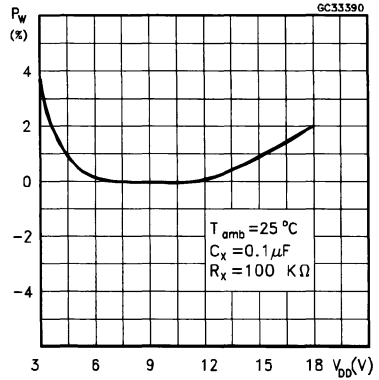
Typical Propagation Delay Time as a Function of Load Capacitance (RESET to Q or Q̄)



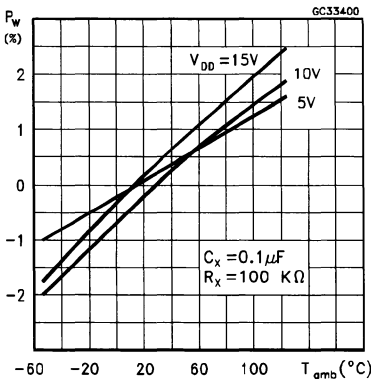
Typical Transition Time as a Function of Load Capacitance



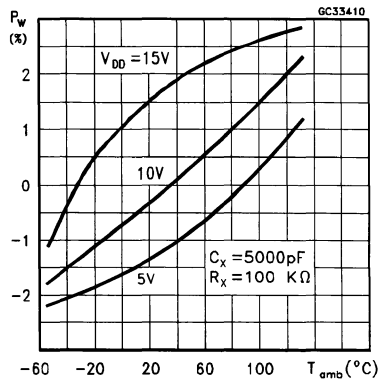
Typical Pulse Width Variation as a Function of Supply Voltage



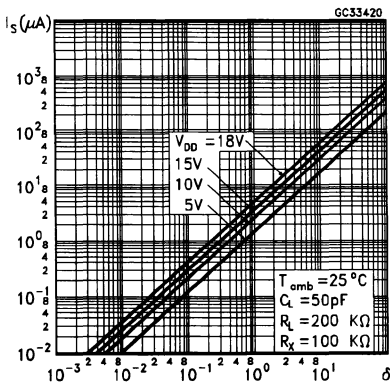
Typical Pulse Width Variation as a Function of Temperature



Typical Pulse Width Variation as a Function of Temperature



Typical Total Supply Current as a Function of Output Duty Cycle



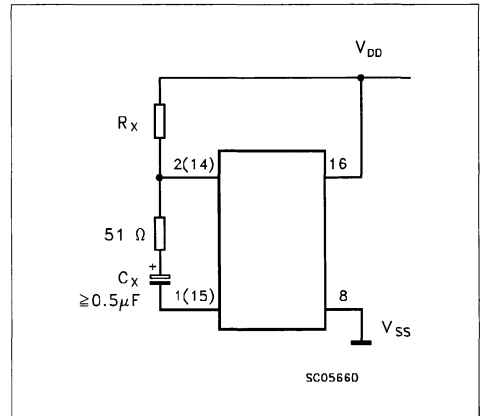
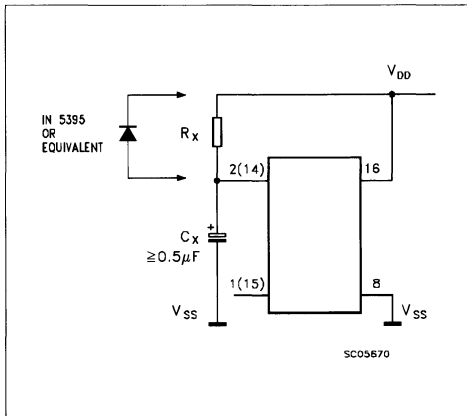
Power Down Mode

During a rapid power-down condition, as would occur with a power supply short circuit or with a poorly filtered power supply, the energy stored in C_X could discharge into Pin 2 or 14. To Avoid possible device damage in this mode, when C_X is ≤ 0.5 microfarad, a protection diode with a 1 Ampere or higher rating (1N5395 or equivalent) and a separate ground return for C_X should be provided as shown in Fig. 1. An alternate protection method is shown in Fig. 2,

where a 51Ω current limit resistor is inserted in series with C_X . Note that a small pulse width decrease will occur however, and R_X must be appropriately increased to obtain the originally desired pulse width.

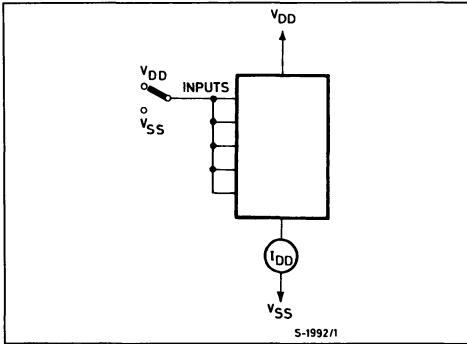
Figure 1: rapid Power Down Protection Circuit

Figure 2: Alternate rapid Power Down Protection Circuit

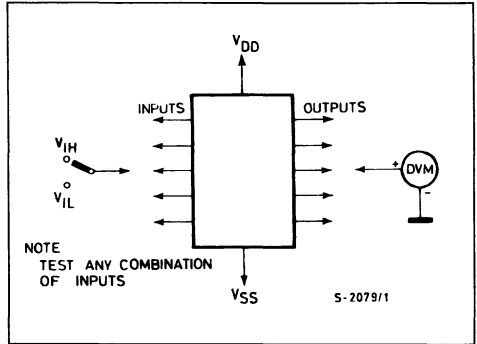


TEST CIRCUITS

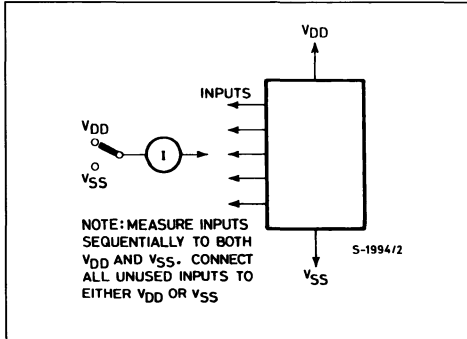
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.



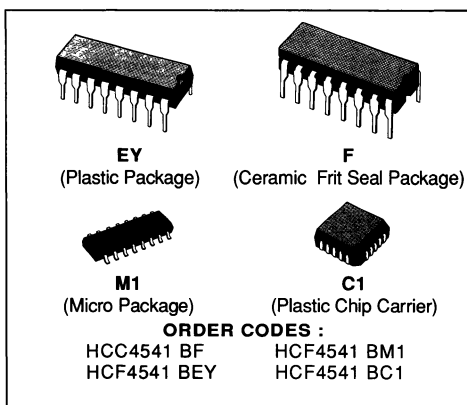
NOTE: MEASURE INPUTS SEQUENTIALLY TO BOTH V_{DD} AND V_{SS} . CONNECT ALL UNUSED INPUTS TO EITHER V_{DD} OR V_{SS}

PROGRAMMABLE TIMER

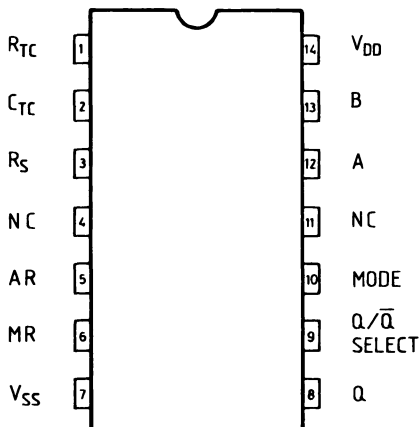
- 16 STAGE BINARI COUNTER
- LOW SYMMETRICAL OUTPUT RESISTANCE, TYPICALLY 100 OHM AT $V_{DD} = 15V$
- OSCILLATOR FREQUENCY RANGE : DC TO 100kHz
- AUTO OR MASTER RESET DISABLES OSCILLATOR DURING RESET TO REDUCE POWER DISSIPATION
- OPERATES WITH VERY SLOW CLOCK RISE AND FALL TIMES
- BUILT-IN LOW-POWER RC OSCILLATOR
- EXTERNAL CLOCK (applied to pin 3) CAN BE USED INSTEAD OF OSCILLATOR
- OPERATES AS 2^N FREQUENCY DIVIDER OR AS A SINGLE-TRANSITION TIMER
- Q/\bar{Q} SELECT PROVIDES OUTPUT LOGIC LEVEL FLEXIBILITY
- CAPABLE OF DRIVING SIX LOW POWER TTL LOADS, THREE LOW-POWER SCHOTTKY LOADS, PR SIX HTL LOADS OVER THE RATED TEMPERATURE RANGE
- SYMMETRICAL OUTPUT CHARACTERISTICS
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- 5-10-15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF 'B' SERIES CMOS DEVICES"

DESCRIPTION

The **HCC/HCF4541B** Programmable Timer is composed of a 16-stage binary counter, an oscillator controlled by 2 external resistors and a capacitor, an output control logic and an automatic power-on reset circuit. The counter varies on positive-edge clock transition and it can be cleared by the MASTER RESET input. The output from this timer is the Q or \bar{Q} output from the 8th, 13th, or 16th counter stage. The choice of the stage depends on the time-select inputs A or B (see frequency selection table). The output is available in one of the two modes that can be selected via the MODE input, pin 10 (see truth table). The output turns out as a continuous square wave, with a frequency equal to the oscillator frequency divided by 2^N . When this MODE



PIN CONNECTION (top view)



SE-0386

input is a logic " 1 ", when it is a logic " 0 " and after a MASTER RESET is started, and Q output has been selected, the output goes up to a high state after 2^{N-1} counts. It remains in that state till another MASTER RESET pulse is apply or the mode input is a logic " 1 ". The process starts by setting the AUTO RESET input (pin 5) to logic " 0 " and switching power on. If pin 5 is set to logic " 1 ", the AUTO RESET circuit is not enabled and counting cannot start till a positive MASTER RESET is applied, returning to a low level. The AUTO RESET con-

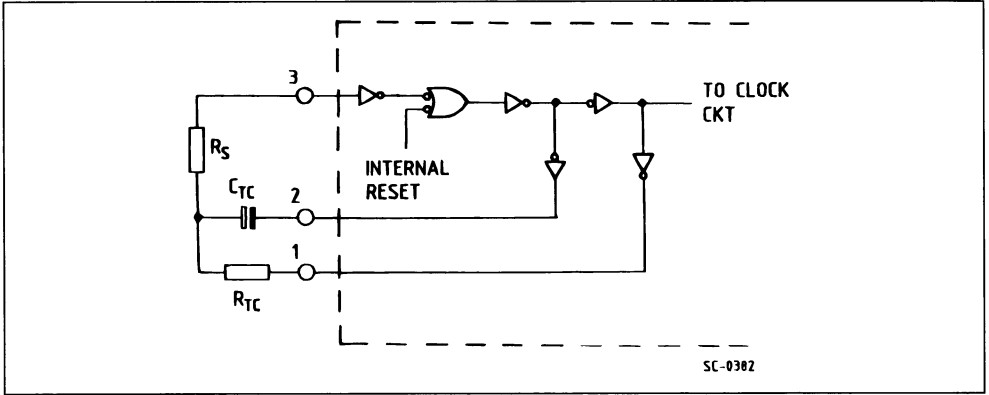
sumes a remarkable amount of power and should not be used if low-power operation is wanted.

The frequency of the oscillator depends on the RC network. It can be calculated using the following formula:

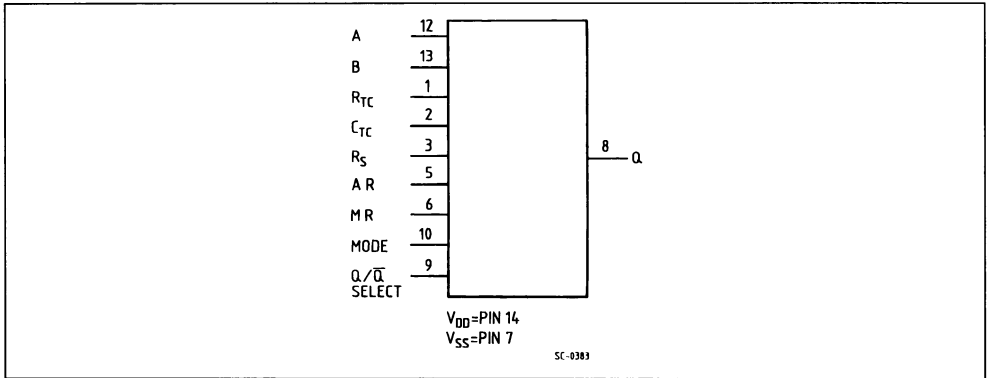
$$f = \frac{1}{2.3 R_{TC} C_{TC}}$$

where f is between 1 kHz and 100 kHz
and $RS \geq 10 \text{ k}\Omega$ and $\approx 2 R_{TC}$

RC Oscillator Circuit.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

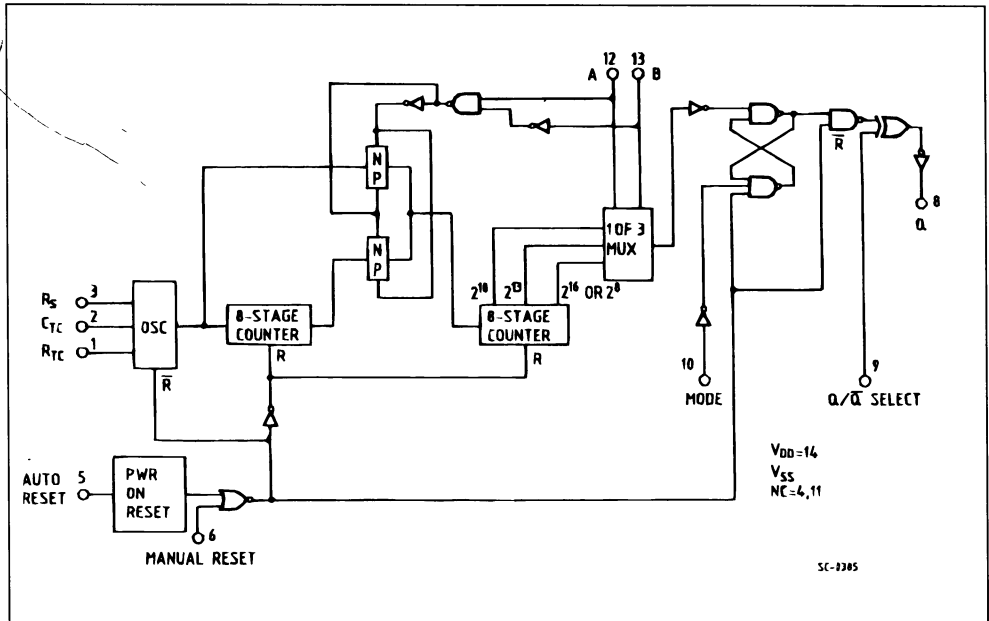
Stresses above those listed under " Absolute Maximum Ratings " may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

* All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to 125	°C
		- 40 to 85	°C

LOGIC DIAGRAM



STATIC ELECTRICAL

Symbol	Parameter		Test Conditions				Value						Unit	
			V _i (V)	V _o (V)	I _o (μ A)	V _{DD} (V)	T _{Low}		25°C			T _{High}		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		5		0.04	5		150	
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95				4.95			
		0/10	< 1	10	9.95		9.95				9.95			
		0/15	< 1	15	14.95		14.95				14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05			0.05		
		10/0	< 1	10		0.05			0.05			0.05		
		15/0	< 1	15		0.05			0.05			0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5			
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5		
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	4.6		5	-1.9		-1.55	-3.1		-1.08		
			0/5	2.5		5	-6.2		-5	-10		-3		
			0/10	9.5		10	-5.0		-4	-8		-2.8		
			0/15	13.5		15	-12.6		-10	-20		-7.2		
		HCF Types	0/5	4.6		5	-1.85		-1.55	-3.1		-1.26		
			0/5	2.5		5	-6.0		-5	-10		-4.1		
			0/10	9.5		10	-4.8		-4	-8		-3.3		
	0/15	13.5		15	-12		-10	-20		-8.4				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	1.9		1.55	3.1		1.08		
			0/10	0.5		10	5.0		4	8		2.8		
			0/15	1.5		15	12.6		10	20		7.2		
		HCF Types	0/5	0.4		5	1.85		1.55	3.1		1.26		
			0/10	0.5		10	4.8		4	8		3.3		
			0/15	1.5		15	12		10	20		8.4		
I _{IH} , I _{IL}	Input Leakage Current	0/18	Any Input		18		± 0.1		$\pm 0.1^{\frac{1}{5}}$	± 0.1		± 1	μ A	
C _i	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = - 55C for HCC device - 40C for HCF device

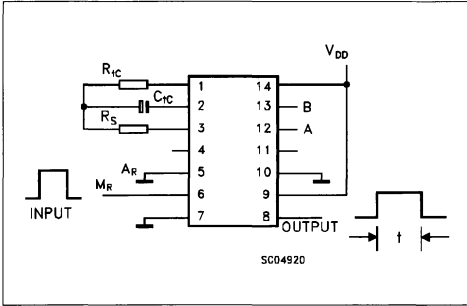
* T_{High} = + 125C for HCC device + 85C for HCF device

The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V 2V min with V_{DD} = 10V 2.5V min with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$,
typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	VDD (V)	Values			Unit
			Min.	Typ.	Max.	
(2^8) t_{PHL} t_{PLH}	Propagation Delay Time Clock to Q	5		3.5	10.5	μs
		10		1.25	3.8	
		15		0.9	2.9	
(2^{16}) t_{PHL} t_{PLH}		5		6	18	μs
		10		3.5	10	
		15		2.5	7.5	
t_{HL}	Transition Time	5		100	200	ns
		10		50	100	
		15		40	80	
t_{LH}		5		180	360	
		10		90	180	
		15		65	130	
	Master Reset, Clock Pulse Width	5	900	300		ns
		10	300	100		
		15	225	85		
f_{CL}	Maximum Clock Pulse Input Frequency	5		1.5		MHz
		10		4		
		15		6		
t_r, t_f	Maximum Clock Pulse Input Rise or Fall Time	5	Unlimited			μs
		10				
		15				

DIGITAL TIMER APPLICATION



A positive MASTER RESET pulse clears the counters and latch. The output goes high and keeps up until the number of pulses, selected by A and B, are counted. This circuit is retriggerable and is as accurate as the input frequency. If a more accurate circuit is desired, an external clock can be used on pin 3. A set-up time equal to the width of the one shot output is required immediately following initial power up, during which time the output will be high.

FREQUENCY SELECTION TABLE

A	B	N ^o of Stages N	Count 2 ^N
0	0	13	8192
0	1	10	1024
1	0	18	256
1	1	16	65536

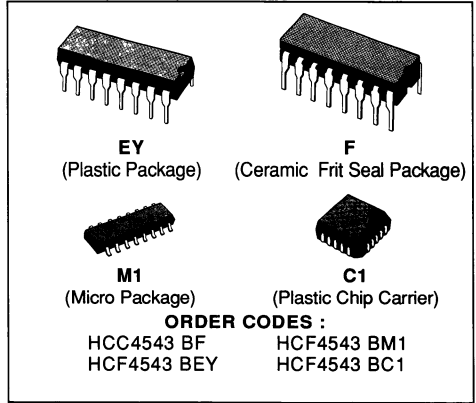
TRUTH TABLE

Pin	State	
	0	1
5	Auto Reset On	Auto Reset Disable
6	Master Reset Off	Master Reset On
9	Output Initially Low After Reset (Q)	Output Initially High After Reset (Q̄)
10	Single Transition Mode	Recycle Mode



BCD-TO-7 SEGMENT LATCH/DECODER/LCD DRIVER

- DISPLAY BLANKING OF ALL ILLEGAL INPUT COMBINATIONS
- LATCH STORAGE OF CODE
- CAPABILITY OF DRIVING TWO LOW POWER TTL LOADS, TWO HTL LOADS, OR ONE LOW POWER SCHOTTKY LOAD OVER THE FULL RATED-TEMPERATURE RANGE
- PIN-FOR-PIN REPLACEMENT FOR THE HCF4056B (with pin 7 tied to V_{SS})
- DIRECT LED DRIVING CAPABILITY
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- MAXIMUM INPUT CURRENT OF 1A AT 18V OVER FULL PACKAGE-TEMPERATURE RANGE ; 100nA AT 18V AND 25°C
- NOISE MARGIN (full package-temperature range) = 1V AT V_{DD} = 5V
2V AT V_{DD} = 10V
2.5V AT V_{DD} = 15V
- 5-V, 10-V, AND 15-V PARAMETRIC RATINGS



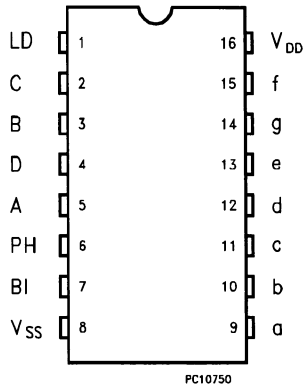
Applications :

- INSTRUMENT DISPLAY DRIVER
- DASHBOARD DISPLAY DRIVER
- COMPUTER/CALCULATOR DISPLAY DRIVER
- TIMING DEVICE DRIVER (clocks, watches, timers)

DESCRIPTION

The HCC/HCF4543B is a BCD-to-seven segment latch/decoder/driver designed primarily for liquid-crystal display (LCD) applications. It is also capable of driving light emitting diode (LED), incandescent, gas-discharge, and fluorescent displays. This device is functionally similar to and serves as direct replacement for the HCF4056B when pin 7 is connected to V_{SS}. It differs from the HCF4056B in that it has a display blanking capability instead of a level-shifting function and requires only one power supply. When the HCF4056B is used in the level shifting mode, two power supplies are required. When the HCF4543B is used for LCD applications, a square wave must be applied to the PHASE input and the backplane of the LCD device. For LED applications a logic 1 is required at the PHASE input for common-cathode devices ; a logic 0 is required for common-anode devices (see truth table).

PIN CONNECTION (top view)

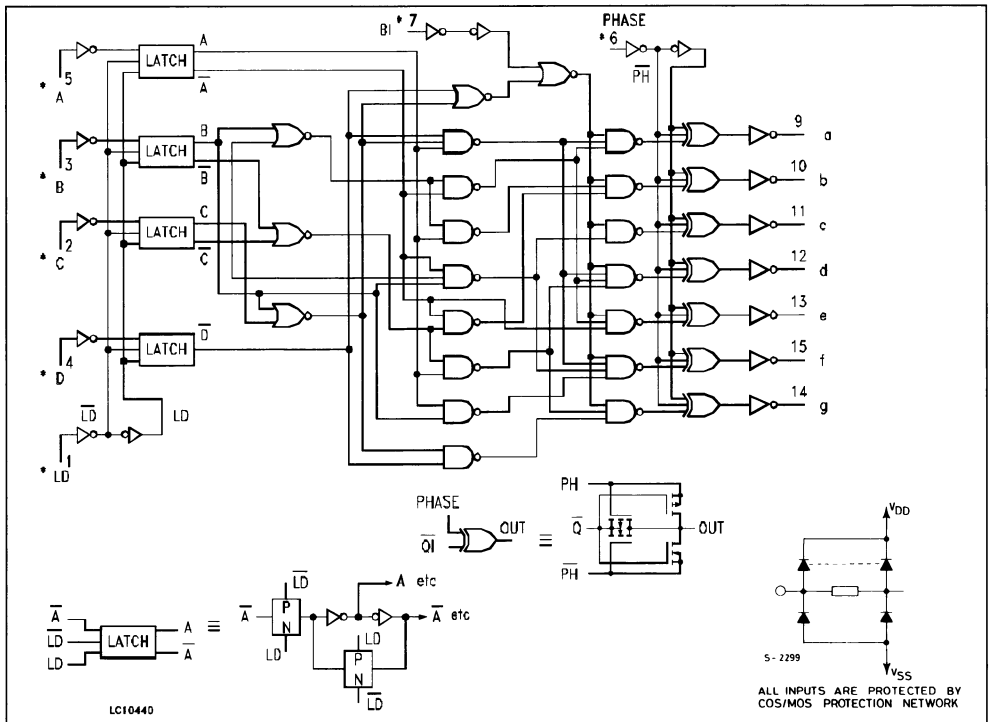


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

* All Voltage Values are referred to V_{SS} pin voltage

LOGIC DIAGRAM (1/2 of device shown)



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC types HCF types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC types HCF types	- 55 to + 125	°C
		- 40 to + 85	°C

TRUTH TABLE

INPUT CODE							OUTPUT STATE							DISPLAY CHARACTER
LD	BI	Ph*	D	C	B	A	a	b	c	d	e	f	g	
X	1	0	X	X	X	X	0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	1	1	1	1	1	1	0	0
1	0	0	0	0	0	1	0	1	1	0	0	0	0	0
1	0	0	0	0	1	0	1	1	0	1	1	0	1	0
1	0	0	0	0	1	1	1	1	1	1	0	0	1	0
1	0	0	0	1	0	0	0	1	1	0	0	1	1	0
1	0	0	0	1	0	1	1	0	1	1	0	1	1	0
1	0	0	0	1	1	0	1	0	1	1	1	1	1	0
1	0	0	0	1	1	1	1	1	1	0	0	0	0	0
1	0	0	1	0	0	0	1	1	1	1	1	1	1	1
1	0	0	1	0	0	1	1	1	1	1	0	1	1	0
1	0	0	1	0	1	0	0	0	0	0	0	0	0	0
1	0	0	1	0	1	1	0	0	0	0	0	0	0	0
1	0	0	1	1	0	1	0	0	0	0	0	0	0	0
1	0	0	1	1	1	0	0	0	0	0	0	0	0	0
1	0	0	1	1	1	1	0	0	0	0	0	0	0	0
0	0	0	X	X	X	X	**							**
.	.	.	.				Inverse of Output Combinations Above							Display as above

X = Don't care.

. = Above combinations

* = For liquid-crystal readouts, apply a square wave to Ph.

For common cathode LED readouts, select Ph = 0.

For common anode LED readouts, select Ph = 1.

** = Depends upon the BCD code previously applied when LD = 1.

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low}		25 °C			T _{High}		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		5		0.04	5		150	
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-1.6		-1.3	-2.6		-0.9	mA	
			0/5	4.6		5	-0.46		-0.37	-0.75		-0.26		
			0/10	9.5		10	-0.98		-0.8	-1.6		-0.55		
			0/15	13.5		15	-3.33		-2.7	-5.4		-1.9		
		HCF Types	0/5	2.5		5	1.3		-1.1	-2.6		-0.9		
			0/5	4.6		5	0.36		-0.31	-0.75		-0.25		
			0/10	9.5		10	0.81		-0.68	-1.6		-0.54		
	0/15	13.5		15	2.7		-2.3	-5.4		-1.84				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

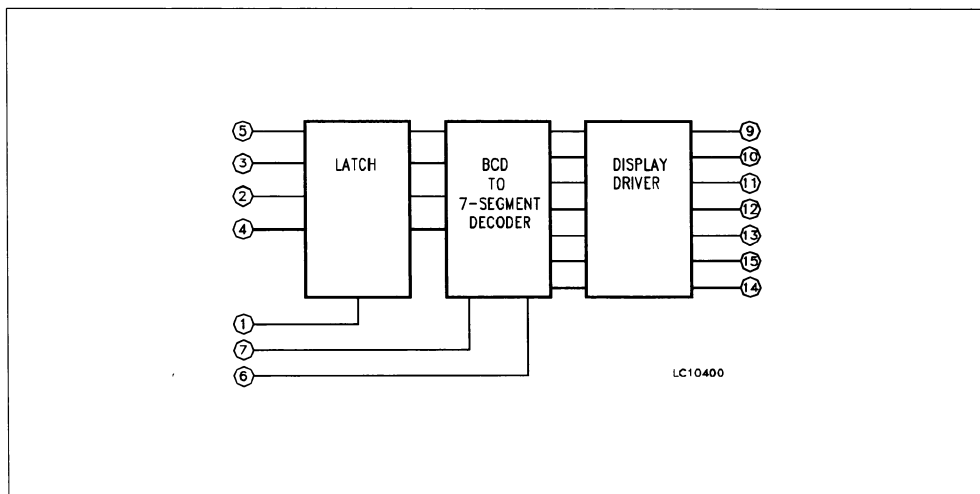
* T_{High} = + 125°C for HCC device + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is $\cdot 1V$ min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

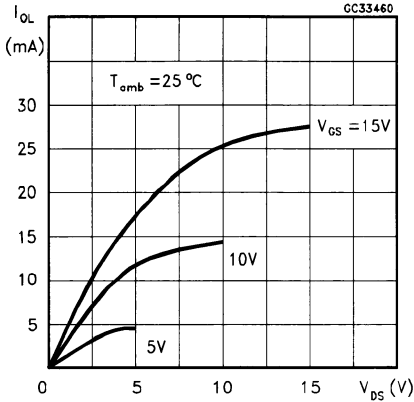
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions V_{DD} (V)	Limits All packages			Unit
			Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time	5		600	1200	ns
		10		200	400	
		15		150	300	
t_{PLH}		5		500	1000	
		10		200	400	
		15		150	300	
t_{THL}	Transition Time	5		180	360	
		10		90	180	
		15		65	130	
t_{TLH}		5		180	360	
		10		90	180	
		15		65	130	
t_{WH}	Latch Disable Pulse Width	5	250	125		
		10	100	50		
		15	80	40		
t_{SU}	Address Setup Time	5	60	15		
		10	20	-5		
		15	10	-5		
t_H	Address Hold Time	5	25	-5		
		10	20	10		
		15	20	0		
C_{IN}	Input Capacitance	Any Input		5	7.5	pF

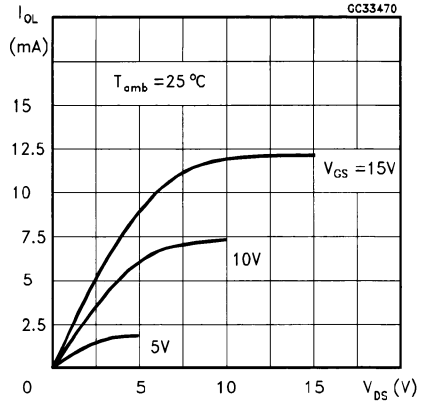
BCD-to-seven-segment latch/decoder/driver functional diagram



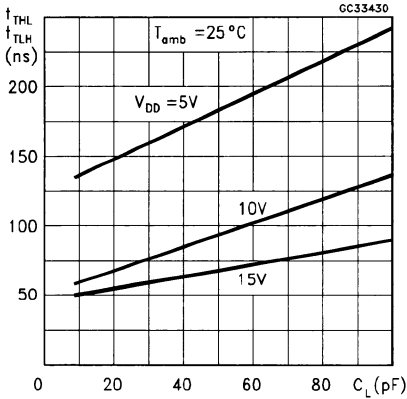
Typical Output Low (sink) Current Characteristics.



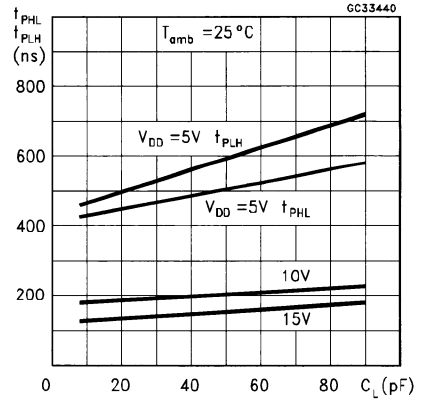
Minimum Output Low (sink) Current Characteristics.



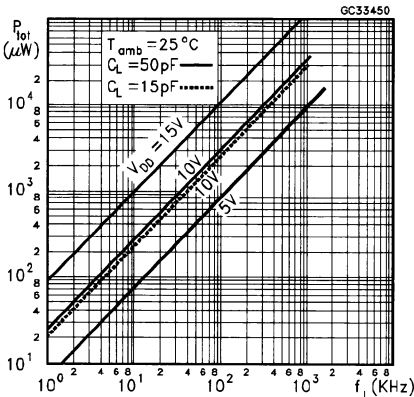
Typical Transition Time as a Function of Load Capacitance



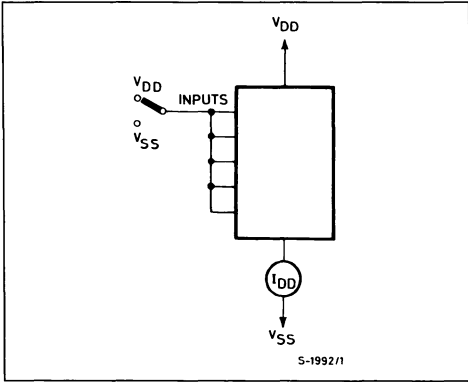
Typical Propagation Delay Time as a Function of Load Capacitance



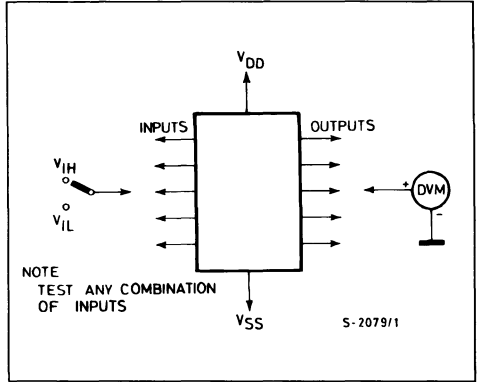
Typical Dynamic Power Dissipation as a Function of Frequency



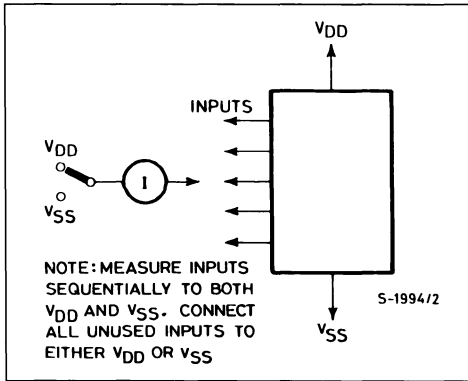
Input Voltage Test Circuit.



Quiescent Device Current Test Circuit.



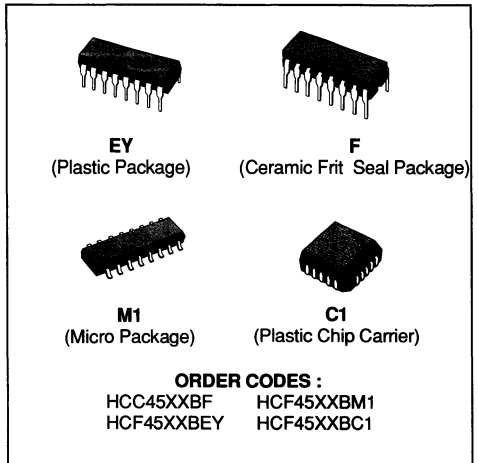
Input-leakage -current Test Circuit.



DUAL BINARY TO 1 OF 4 DECODER/DEMULTIPLEXERS

4555B OUTPUTS HIGH ON SELECT
4556B OUTPUTS LOW ON SELECT

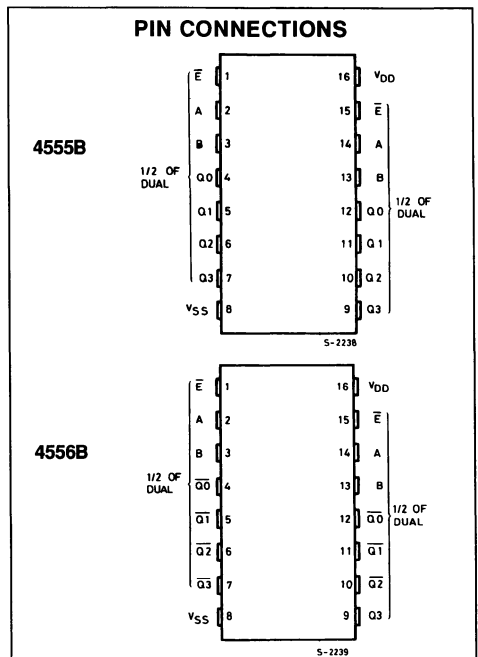
- EXPANDABLE WITH MULTIPLE PACKAGES
- STANDARD, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



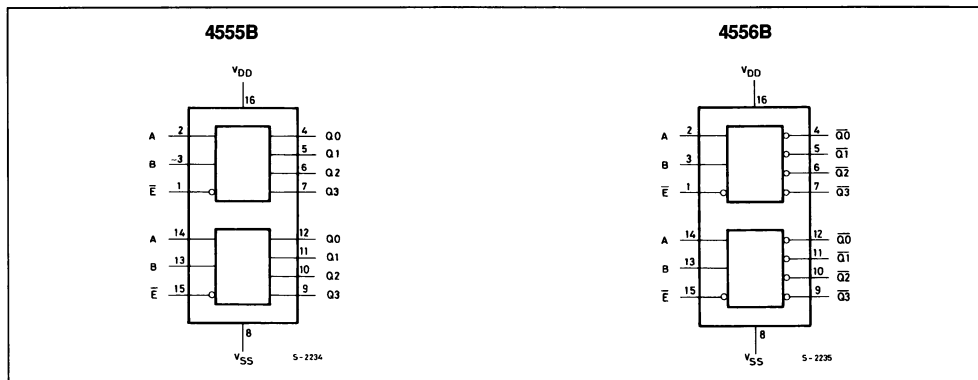
DESCRIPTION

The **HCC4555B**, **HCC4556B** (extended temperature range) and the **HCF4555B**, **HCF4556B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4555B** and **HCC/HCF4556B** are dual one-of-four decoders/demultiplexers. Each decoder has two select inputs (A and B), an Enable input (E), and four mutually exclusive outputs. On the **HCC/HCF4555B** the outputs are high on select; on the **HCC/HCF4556B** the outputs are low on select. When the Enable input is high, the outputs of the **HCC/HCF4555B** remain low and the outputs of the **HCC/HCF4556B** remain high regardless of the state of the select inputs A and B.



FUNCTIONAL DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

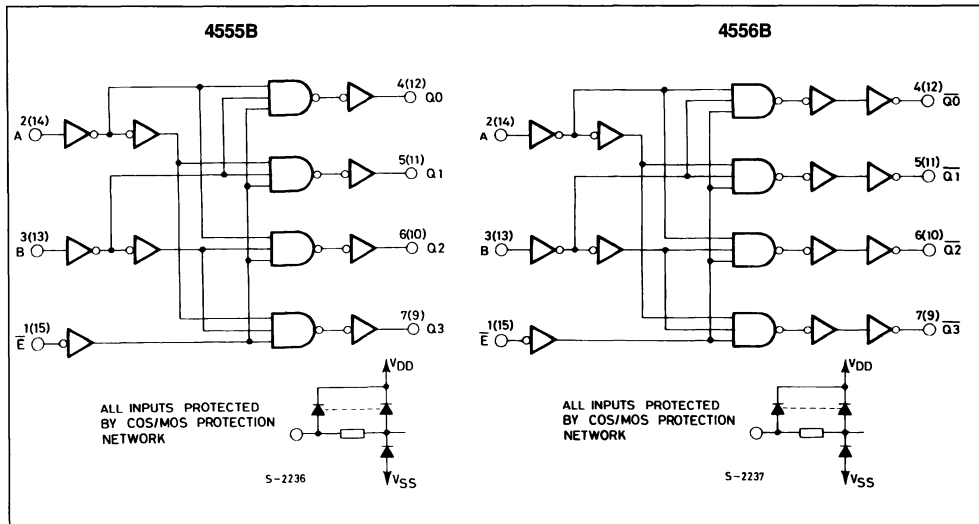
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltages values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS



TRUTH TABLE

Inputs Enable Select			Outputs 4555B				Outputs 4556B			
\bar{E}	B	A	Q3	Q2	Q1	Q0	$\bar{Q3}$	$\bar{Q2}$	$\bar{Q1}$	$\bar{Q0}$
0	0	0	0	0	0	1	1	1	1	0
0	0	1	0	0	1	0	1	1	0	1
0	1	0	0	1	0	0	1	0	1	1
0	1	1	1	0	0	0	0	1	1	1
1	X	X	0	0	0	0	1	1	1	1

X = DON'T CARE, LOGIC 1 = HIGH, LOGIC 0 = LOW

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
	HCF Types	0/ 5			5		20		0.04	20		150		
		0/10			10		40		0.04	40		300		
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		$\pm 10^{-5}$	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

(*) T_{LOW} = - 55°C for HCC device : - 40°C for HCF device

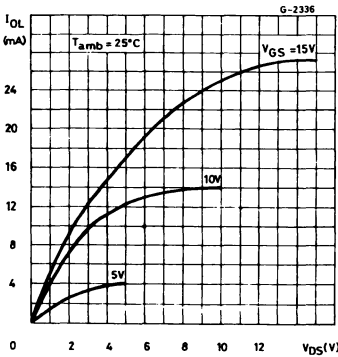
(*) T_{HIGH} = + 125°C for HCC device . + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V

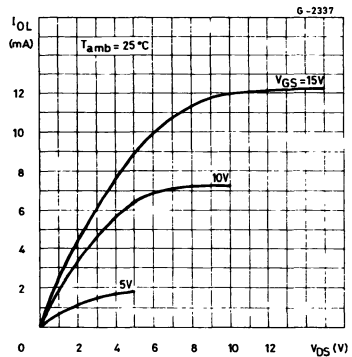
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time (A or B input to any output)		5		220	440	ns
			10		95	190	
			15		70	140	
	Propagation Delay Time (E input to any output)		5		200	400	ns
			10		85	170	
			15		65	130	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

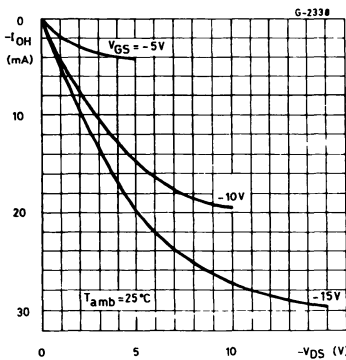
Typical Output Low (sink) Current Characteristics.



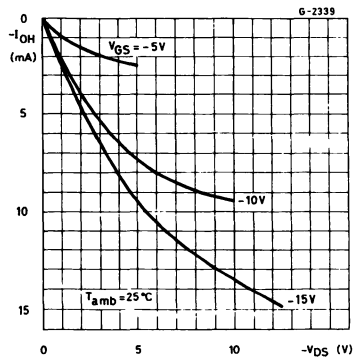
Minimum Output Low (sink) Current Characteristics.



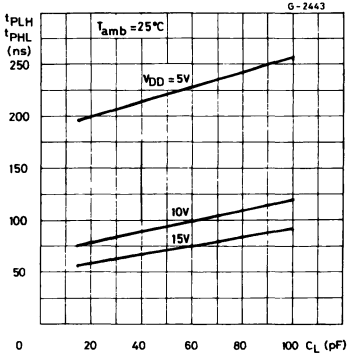
Typical Output High (source) Current Characteristics.



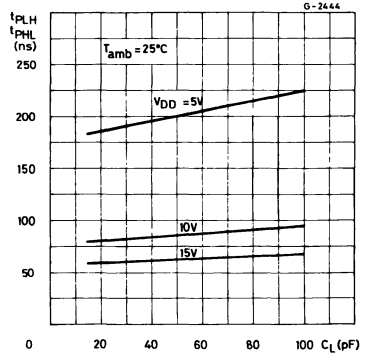
Minimum Output High (source) Current Characteristics.



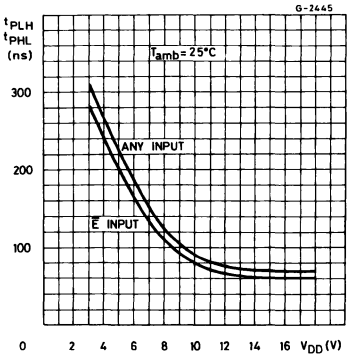
Typical Propagation Delay Time vs. Load Capacitance (A or B input to any output).



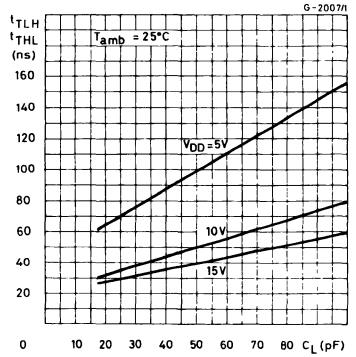
Typical Propagation Delay Time vs. Load Capacitance (E input to any input).



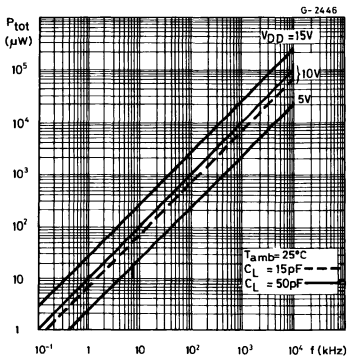
Typical Propagation Delay Time vs. Supply Voltage.



Typical Transition Time vs. Load Capacitance.

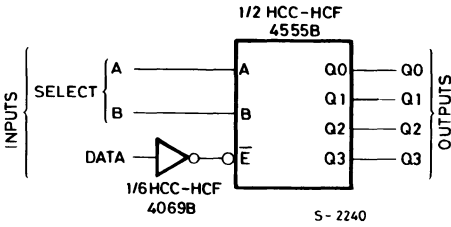


Typical Dynamic Power Dissipation/per Device vs. Frequency.



APPLICATIONS

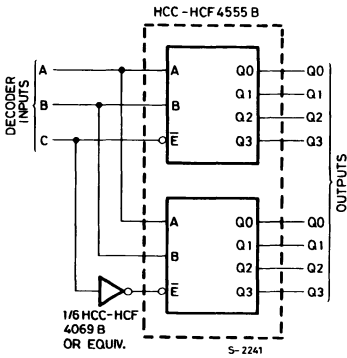
1 of 4 Line Data Demultiplexer using HCC/HCF4555B



TRUTH TABLE

Select Inputs		Outputs			
B	A	Q0	Q1	Q2	Q3
0	0	DATA	0	0	0
0	1	0	DATA	0	0
1	0	0	0	DATA	0
1	1	0	0	0	DATA

1 of 8 Decoder using HCC/HCF 4555B

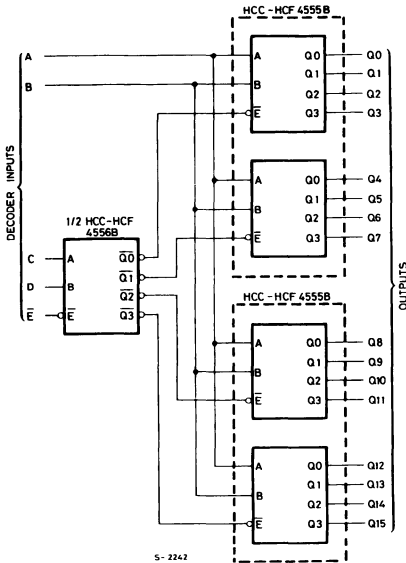


TRUTH TABLE

Inputs			Q Outputs							
C	B	A	0	1	2	3	4	5	6	7
0	0	0	1	0	0	0	0	0	0	0
0	0	1	0	1	0	0	0	0	0	0
0	1	0	0	0	1	0	0	0	0	0
0	1	1	0	0	0	1	0	0	0	0
1	0	0	0	0	0	0	1	0	0	0
1	0	1	0	0	0	0	0	1	0	0
1	1	0	0	0	0	0	0	0	1	0
1	1	1	0	0	0	0	0	0	0	1

APPLICATIONS (continued)

1 of 16 Decoder using HCC/HCF4555B and HCC/HCF4556B

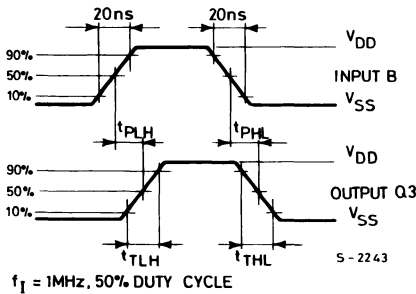


TRUTH TABLE

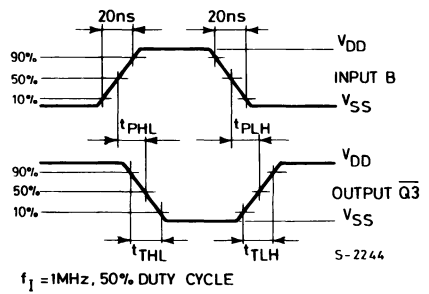
Inputs					Q Outputs																
E	D	C	B	A	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	
0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	0	0	1	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	0	1	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	0	1	1	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0
0	0	1	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0
0	0	1	0	1	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	0
0	0	1	1	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0
0	0	1	1	1	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0
0	1	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0
0	1	0	0	1	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	0
0	1	0	1	1	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0
0	1	1	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0
0	1	1	0	1	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	0
0	1	1	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0
0	1	1	1	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1
1	X	X	X	X	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

X = Don't care.

HCC/HCF4555B Input to Q3 Output Dynamic Signal Waveforms

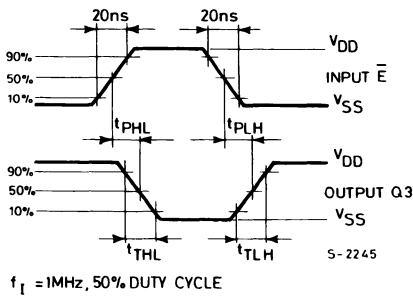


HCC/HCF4556B Input to Q3 Output Dynamic Signal Waveforms

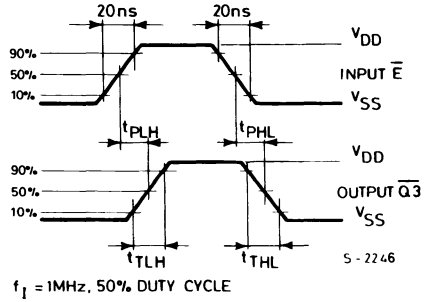


APPLICATIONS (continued)

HCC/HCF4555B \bar{E} Input to Q3 Output Dynamic Signal Waveforms

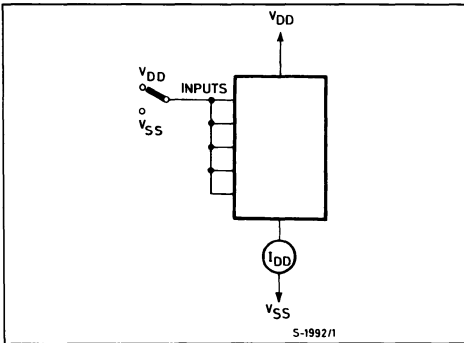


HCC/HCF4556B \bar{E} Input to $\bar{Q}3$ Output Dynamic Signal Waveforms

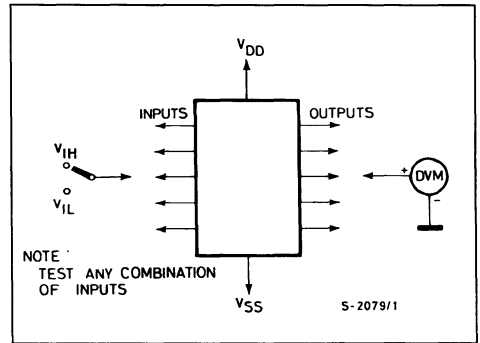


TEST CIRCUITS

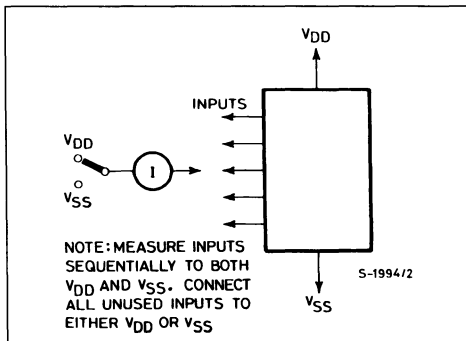
Quiescent tDevice Current.



Noise Immunity.



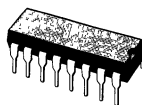
Input Leakage Current.



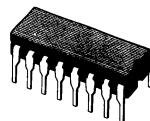
NBCD ADDER

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SINGLE SUPPLY OPERATION - POSITIVE OR NEGATIVE
- SUPPLY VOLTAGE RANGE 3V TO 18V
- DIODE PROTECTION ON ALL INPUTS



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)



C1
(Plastic Chip Carrier)

ORDER CODES :

HCC4560 BF	HCF4560 BM1
HCF4560 BEY	HCF4560 BC1

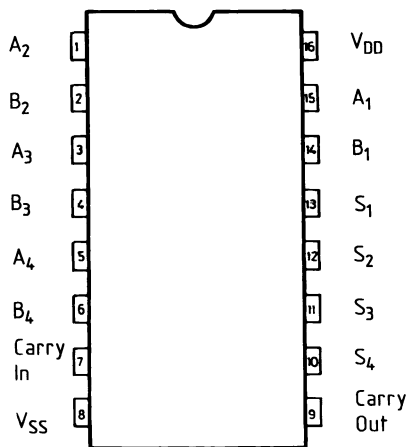
DESCRIPTION

The HCC4560B and HCF4560B are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages and plastic micro packages.

The HCC4560B and HCF4560B add two 4-bit numbers in NBCD (natural binary coded decimal) format, resulting in sum and carry outputs in NBCD code.

All inputs and outputs are active high. The carry input for the least significant digit is connected to V_{SS} for no carry in.

PIN CONNECTION (top view)

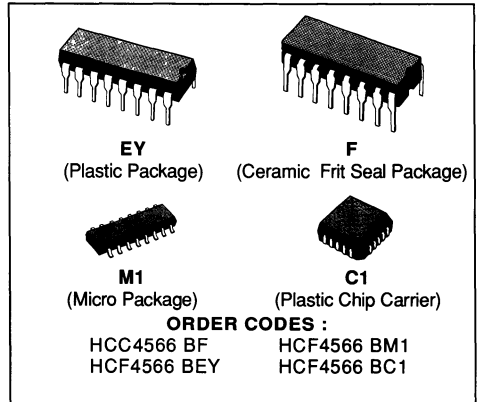


SC-0396

INDUSTRIAL TIME-BASE GENERATOR

PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SUPPLY VOLTAGE RANGE 3V TO 18V
- NEGATIVE EDGE TRIGGERED COUNTERS FOR EASY CASCADING
- PULSE SHAPING ON COUNTER INPUTS ACCEPTS SLOW INPUT RISE TIMES
- MONOSTABLE MULTIVIBRATOR POSITIVE OR NEGATIVE EDGE TRIGGERED



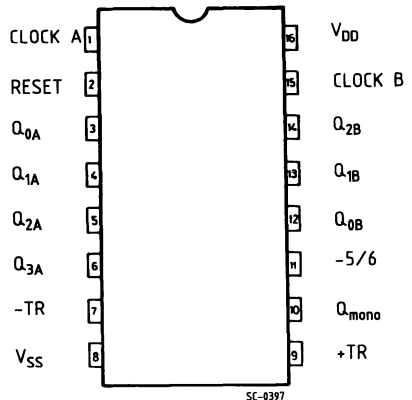
DESCRIPTION

The HCC4566B and HCF4566B are monolithic integrated circuits, available in 16-lead dual-in-line plastic or ceramic packages and plastic micro packages.

The HCC4566B and HCF4566B are industrial time base generators. They consist of a divide-by-10 ripple counter and a divide-by-5 or divide-by-6 ripple counter to permit stable time generation from a 50 or 60Hz line.

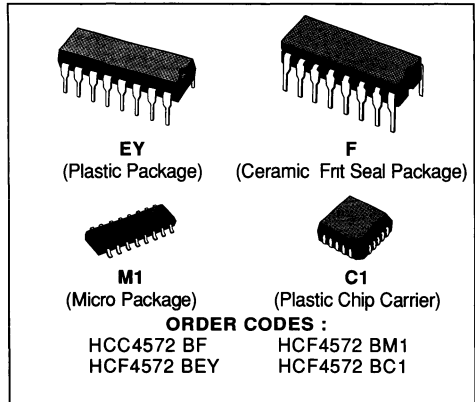
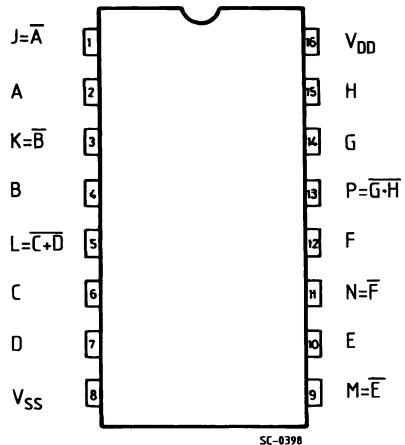
Cascading these devices as divide by 60 counters provides a seconds and minutes counter with an output in BCD format. An internal monostable multivibrator is included whose output can be used as a reset or clock pulse providing additional frequency flexibility. A divide-by-5 facility allows the generation of a 1Hz signal from the European 50Hz-line.

PIN CONNECTION (top view)



HEX GATE
PRODUCT PREVIEW

- VERY LOW QUIESCENT CURRENT
- HIGH NOISE IMMUNITY
- SINGLE SUPPLY OPERATION
- SUPPLY VOLTAGE RANGE 3V TO 18V
- HIGH INPUT IMPEDANCE
- PIN LAYOUT OPTIMISED FOR MAXIMUM FLEXIBILITY

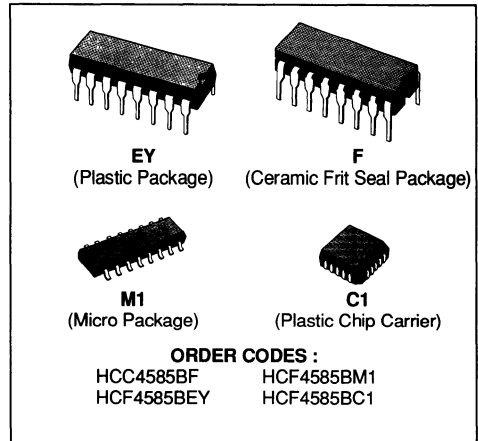

PIN CONNECTION (top view)

DESCRIPTION

The HCC4572B and HCF4572B are monolithic integrated circuits, available in 16-lead dual-in-line plastic and ceramic packages and plastic micro packages.

The HCC4572B and HCF4572B are hex functional gates containing one NOR gate, one NAND gate and four inverters. These devices are intended for application where low power dissipation and/or high noise immunity is required.

4-BIT MAGNITUDE COMPARATOR

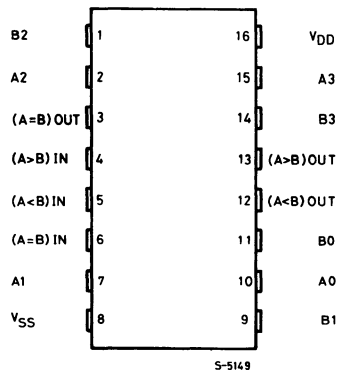
- EXPANSION TO 8, 12, 16 ... 4 N BITS BY CAS-CADING UNITS
- MEDIUM-SPEED OPERATION : COMPARES TWO 4-BIT WORDS IN 180ns (typ.) AT 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



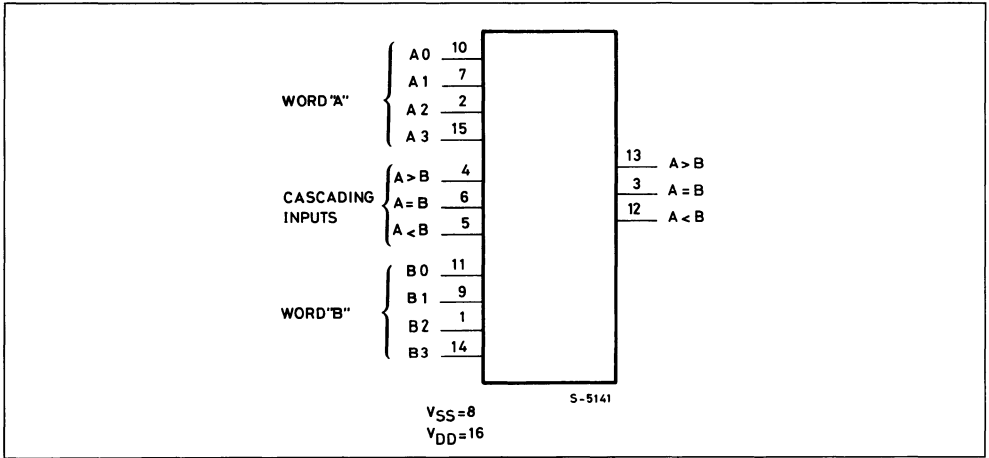
DESCRIPTION

The **HCC4585B** (extended temperature range) and **HCF4585B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package, and plastic micro package. The **HCC/HCF4585B** is a 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to", or "greater than" a second 4-bit word. The **HCC/HCF4585B** has eight comparing inputs (A3, B3, through A0, B0), three outputs (A < B, A = B, A > B) and three cascading inputs (A < B, A = B, A > B) that permit systems designers to expand the comparator function to 8, 12, 16 ... 4 N bits. When a single **HCC/HCF4585B** is used, the cascading inputs are connected as follows : (A < B) = low, (A = B) = high, (A > B) = high. Cascading these units for comparison of more than 4 bits is accomplished as shown in typical application.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

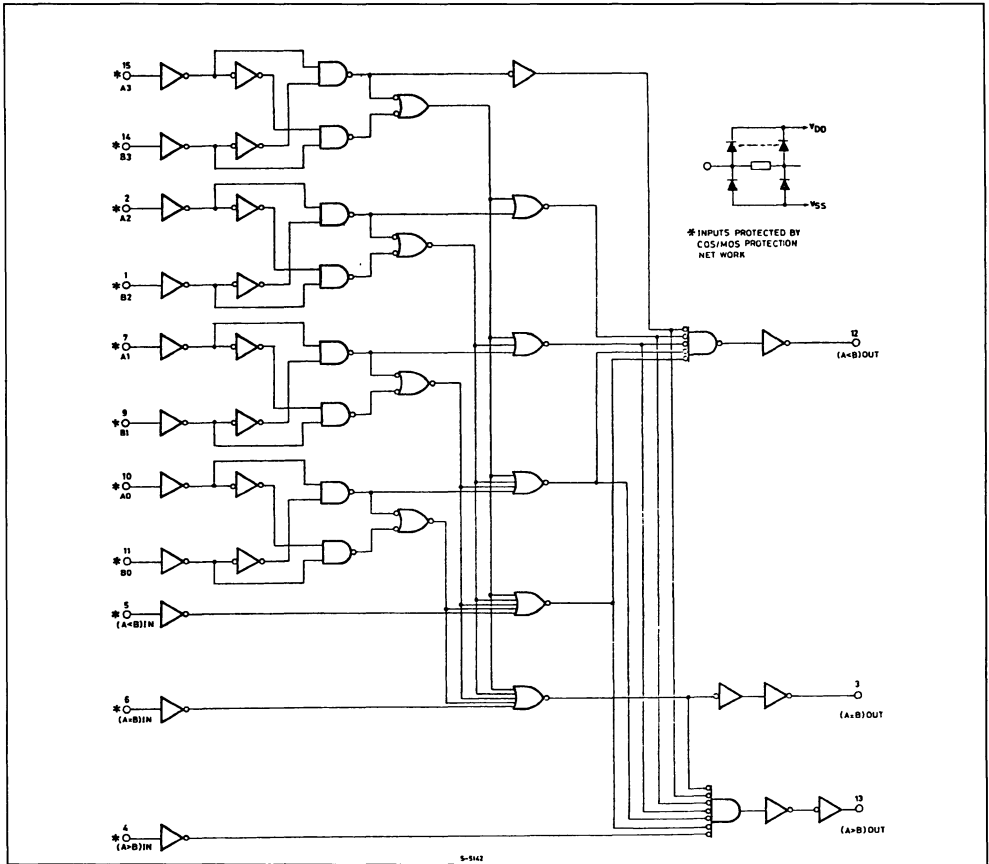
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltages are with respect to V_{SS} (GND)

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

Inputs							Outputs		
Comparing				Cascading					
A3, B3	A2, B2	A1, B1	A0, B0	A < B	A = B	A > B	A < B	A = B	A > B
A3 > B3	X	X	X	X	X	1	0	0	1
A3 = B3	A2 > B2	X	X	X	X	1	0	0	1
A3 = B3	A2 = B2	A1 > B1	X	X	X	1	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	1	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	0	1	0	0	1
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	1	X	0	1	0
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	0	X	1	0	0
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	1	0	0
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	1	0	0
A3 = B3	A2 < B2	X	X	X	X	X	1	0	0
A3 < B3	X	X	X	X	X	X	1	0	0

X = Don't Care

Logic 1 = High Level

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95				4.95		V	
		0/10	< 1	10	9.95		9.95				9.95			
		0/15	< 1	15	14.95		14.95				14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05				0.05		0.05	V	
		10/0	< 1	10		0.05				0.05		0.05		
		15/0	< 1	15		0.05				0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			15/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _i	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device

* T_{High} = + 125°C for HCC device + 85°C for HCF device.

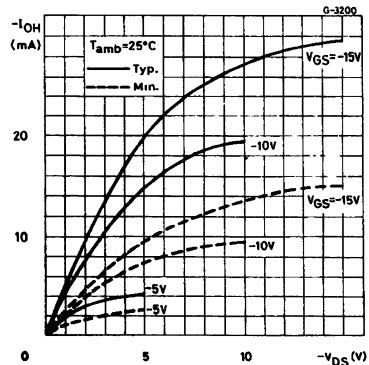
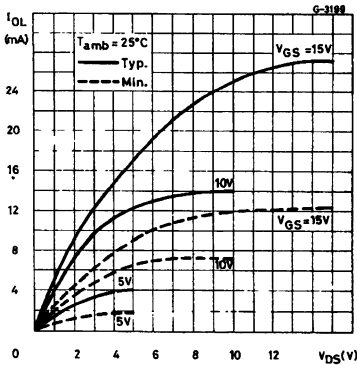
The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time Comparing Inputs to Outputs		5		300	600	ns
			10		125	250	
			15		80	160	
	Cascading Input to Outputs		5		200	400	ns
			10		80	160	
			15		60	120	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

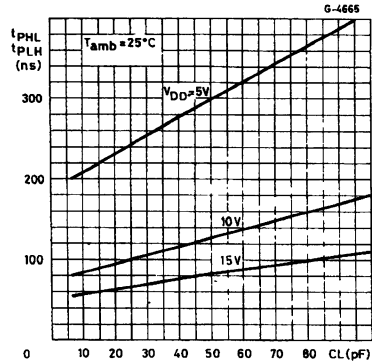
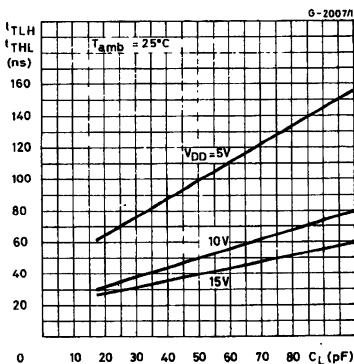
Output Low (sink) Current Characteristics.

Output High (source) Current Characteristics.

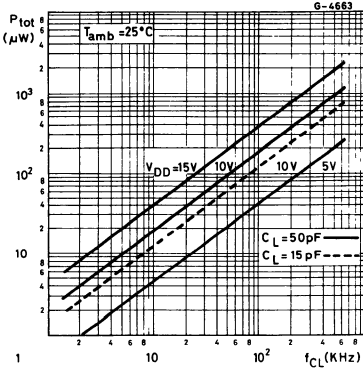


Typical Transition Time vs. Load Capacitance.

Typical Propagation Delay Time (comparing inputs to outputs) vs. Load Capacitance.

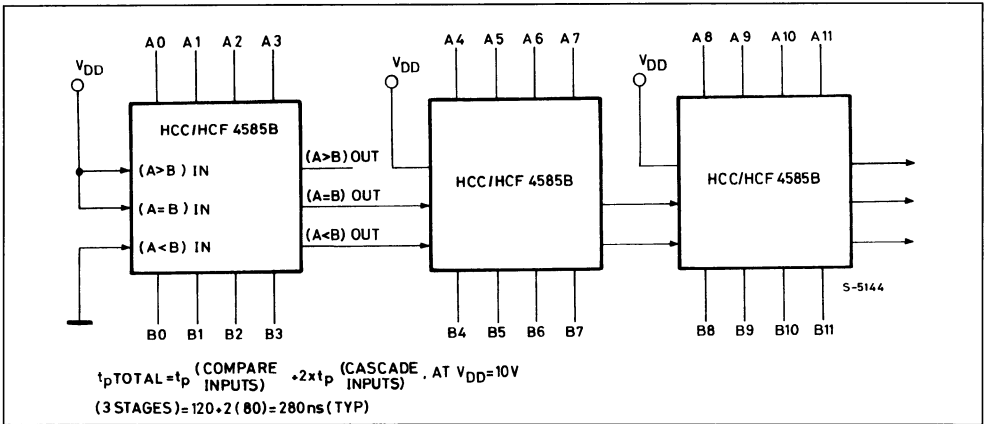


Typical Dynamic Power Dissipation vs. Clock Input Frequency.



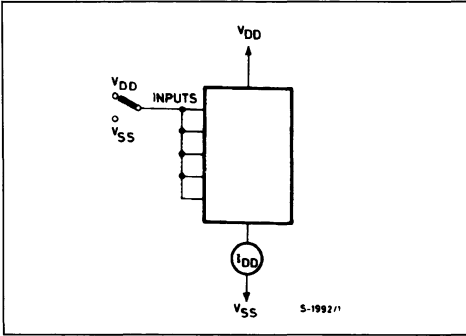
TYPICAL APPLICATION

TYPICAL SPEED CHARACTERISTICS OF A 12-BIT COMPARATOR

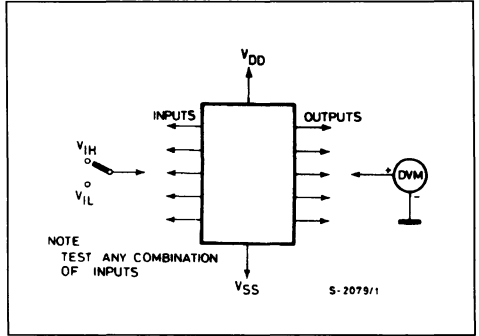


TEST CIRCUITS

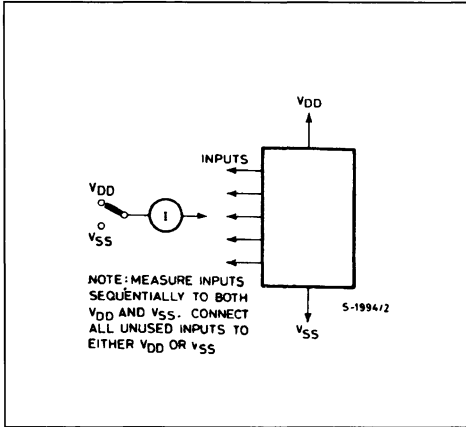
Quiescent Device Current.



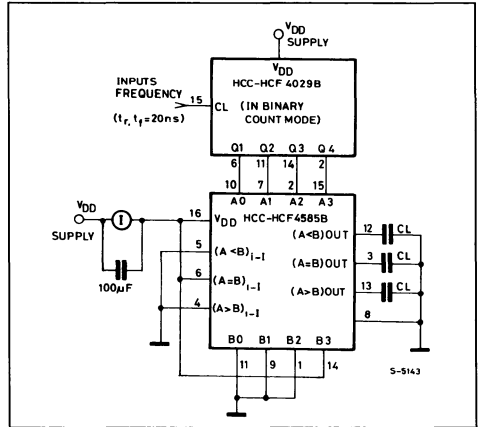
Input Voltage.

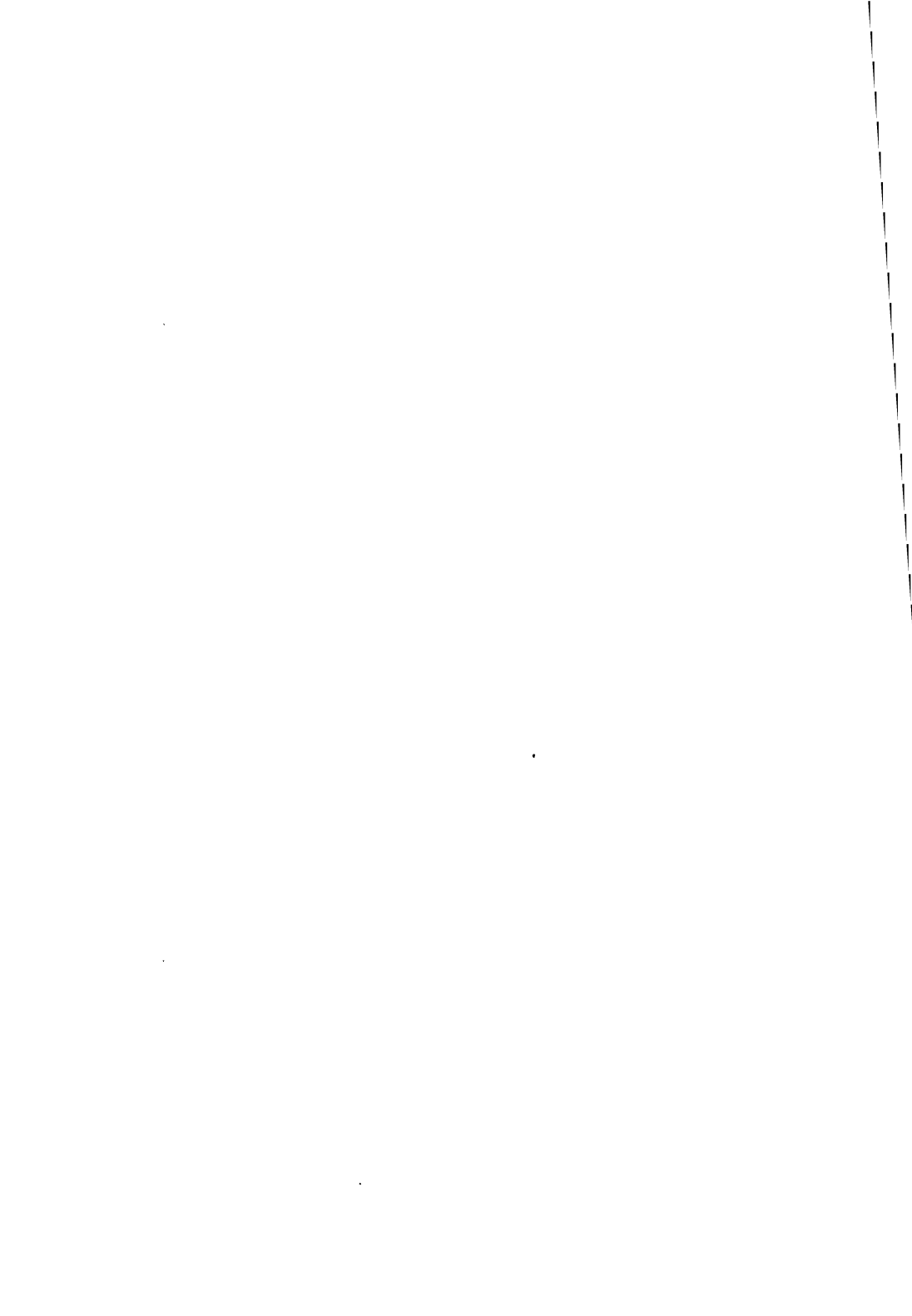


Input Leakage Current.



Dynamic Power Dissipation.





8 BIT ADDRESSABLE LATCH

- SERIAL DATA INPUT - ACTIVE PARALLEL OUTPUT
- STORAGE REGISTER CAPABILITY - MASTER CLEAR
- CAN FUNCTION AS DEMULTIPLEXER
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTER
- 100% TESTED FOR QUIESCENT CURRENT AT 20V
- MAXIMUM INPUT CURRENT OF 1 μ A AT 18V (full package-temperature range), 100nA AT 18V AND 25°C
- NOISE MARGIN (full package-temperature range) = 1V AT $V_{DD} = 5V$, 2V AT $V_{DD} = 10V$, 2.5V AT $V_{DD} = 15V$
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF 'B' SERIES CMOS DEVICES"

APPLICATION

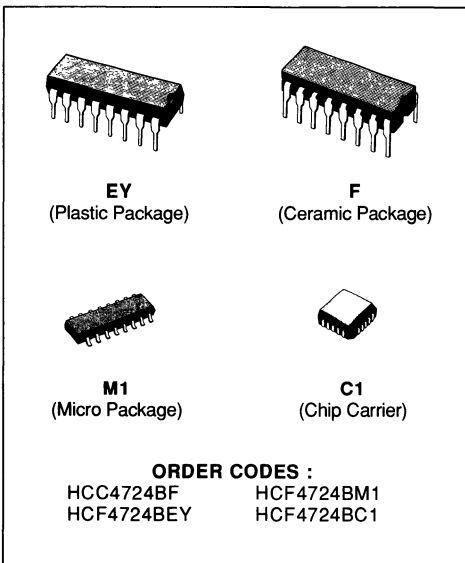
- MULTI-LINE DECODERS
- A/D CONVERTERS

DESCRIPTION

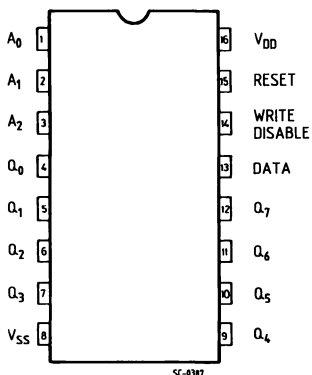
The **HCC/HCF4724B** 8-bit addressable latch is a serial-input, parallel-output storage register that can perform a variety of functions.

Data are inputted to a particular bit in the latch when that bit is addressed (by means of inputs A0, A1, A2) and when WRITE DISABLE is at low level. When WRITE DISABLE is high, data entry is inhibited however, all 8 outputs can be continuously read independent of WRITE DISABLE and address inputs.

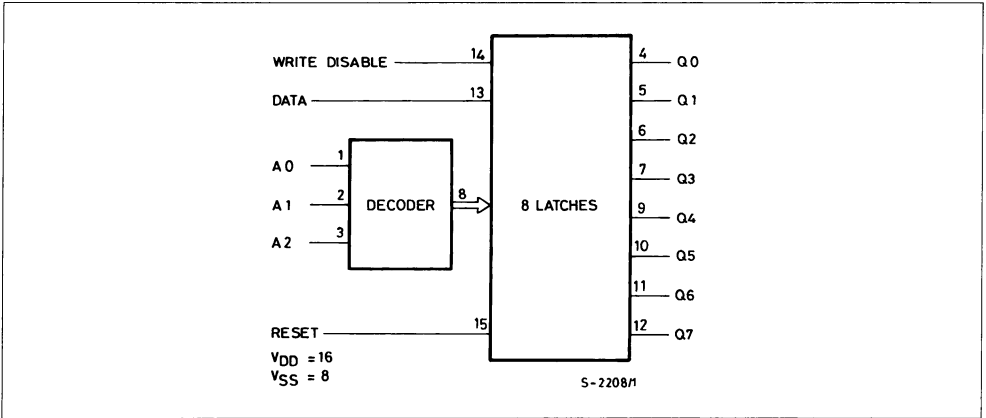
A master RESET input is available, which resets all bits to a logic "0" level when RESET and WRITE DISABLE are at a high level. When RESET is at a high level, and WRITE DISABLE is at a low level, the latch acts as a 1-of-8 demultiplexer; the bit that is addressed has an active output which follows the data input, while all unaddressed bits are held to a logic "0" level.



PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

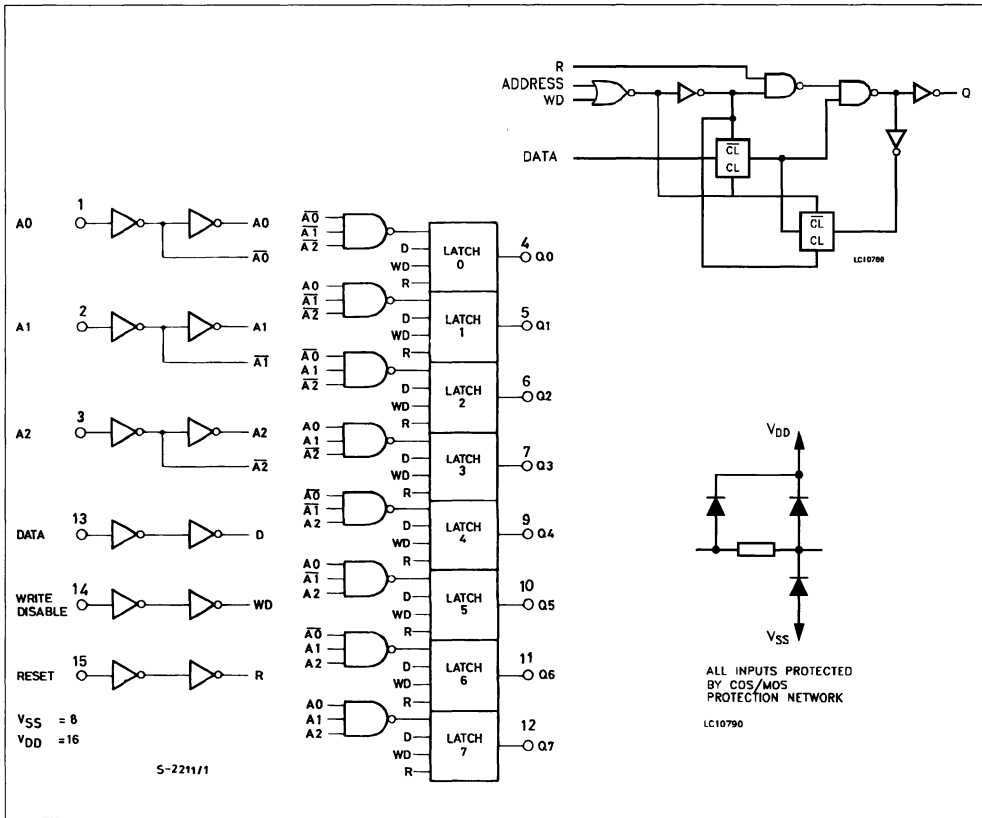
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage

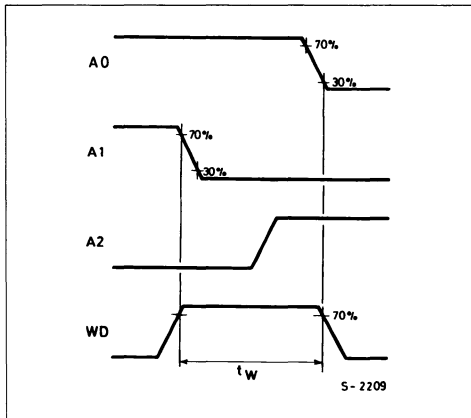
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

LOGIC DIAGRAM



Definition of WRITE DISABLE ON Time



MODE SELECTION

TYPE	WD	R	Addressed Latch	Unaddressed Latch
A	0	0	Follows Data	Hold Previous State
B	0	1	Follows Data (Active High 8-Channel Demultiplexer)	Reset to "0"
C	1	0	Hold Previous State	
D	1	1	Reset to "0"	Reset to "0"

WD = WRITE DISABLE R= RESET

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5	0.04	5		150	μ A	
			0/10			10		10	0.04	10		300		
			0/15			15		20	0.04	20		600		
			0/20			20		100	0.08	100		3000		
		HCF Types	0/5			5		20	0.04	20		150		
			0/10			10		40	0.04	40		300		
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95	V		
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05	0.05	V		
		10/0		< 1	10		0.05			0.05	0.05			
		15/0		< 1	15		0.05			0.05	0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5	1.5	V		
			9/1	< 1	10		3			3	3			
			13.5/1.5	< 1	15		4			4	4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.8		-1.6	-3.2		-1.3		
			0/5	4.6		5	-0.61		-0.51	-1		-0.42		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.61		0.51	1		0.42		
			0/10	0.5		10	1.5		1.3	2.6		1.1		
			0/15	1.5		15	4		3.4	6.8		2.8		
I _{IH} , I _{IL}	Input Leakage Current	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
C _I	Input Capacitance		Any Input					5	7.5				pF	

* T_{Low} = -55 °C for HCC device, -40 °C for HCF device

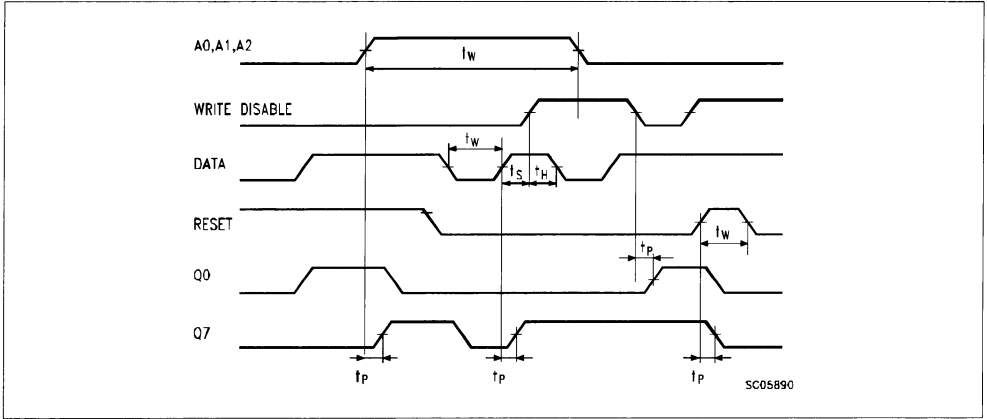
* T_{High} = +125 °C for HCC device +85 °C for HCF device

The Noise Margin for both "1" and "0" level is, 1V min with V_{DD} = 5 V, 2 V min with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

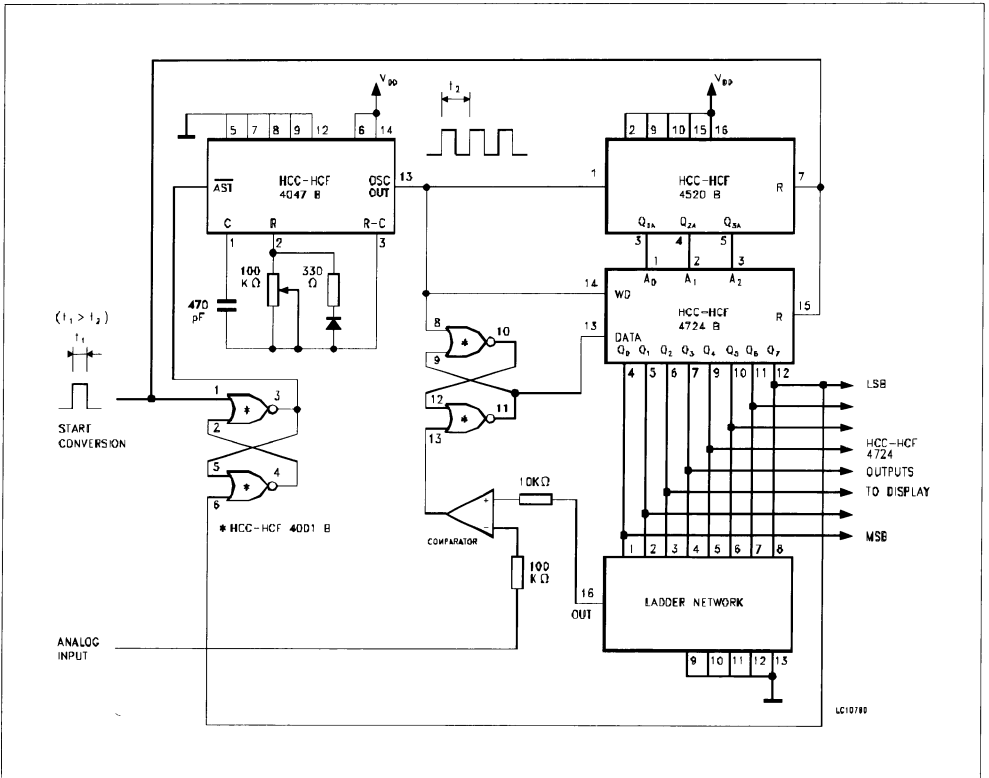
Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
t_{PLH} t_{PHL}	Propagation Delay Time Data to Output	(See Figure 1)	5		200	400	ns
			10		75	150	
			15		50	100	
t_{PLH} t_{PHL}	Propagation Delay Time Write Disable to Output	(See Figure 1)	5		200	400	ns
			10		80	160	
			15		60	120	
t_{PHL}	Propagation Delay Time Reset to Output	(See Figure 1)	5		175	350	ns
			10		80	160	
			15		65	130	
t_{PLH} t_{PHL}	Propagation Delay Time Address to Output	(See Figure 1)	5		225	450	ns
			10		100	200	
			15		75	150	
t_{TLH} t_{THL}	Transition Time Any Output		5		100	200	ns
			10		50	100	
			15		40	80	
tw	Minimum Pulse Width Data	(See Figure 1)	5		100	200	ns
			10		50	100	
			15		40	80	
	Minimum Pulse Width Address	(See Figure 1)	5		200	400	ns
			10		100	200	
			15		65	125	
	Minimum Pulse Width Reset	(See Figure 1)	5		75	150	ns
			10		40	75	
			15		25	50	
t_s	Minimum Setup Time Data to Write Disable	(See Figure 1)	5		50	100	ns
			10		25	50	
			15		20	35	
t_H	Minimum Hold Time Data to Write Disable	(See Figure 1)	5		75	150	ns
			10		40	75	
			15		25	50	
C_{IN}	Input Capacitance		Any Input		5	7.5	pF

Figure 1: Master Timing Diagram

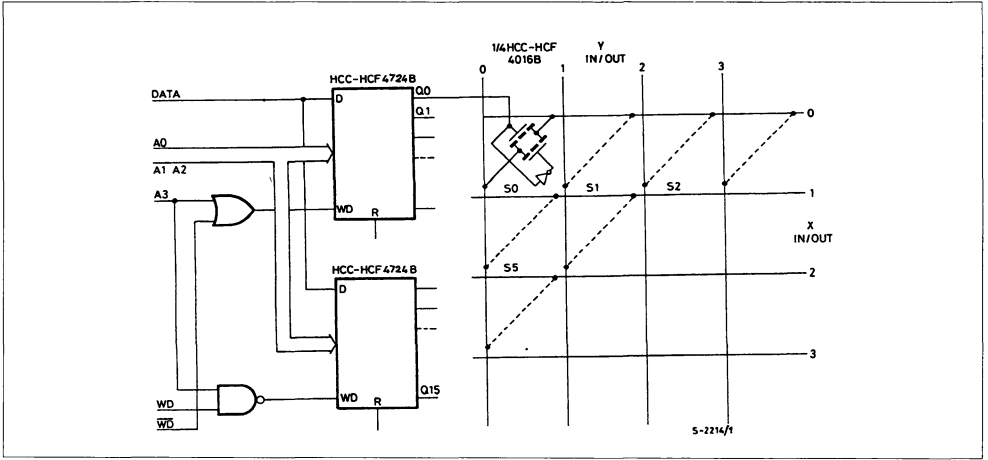


TYPICAL APPLICATIONS

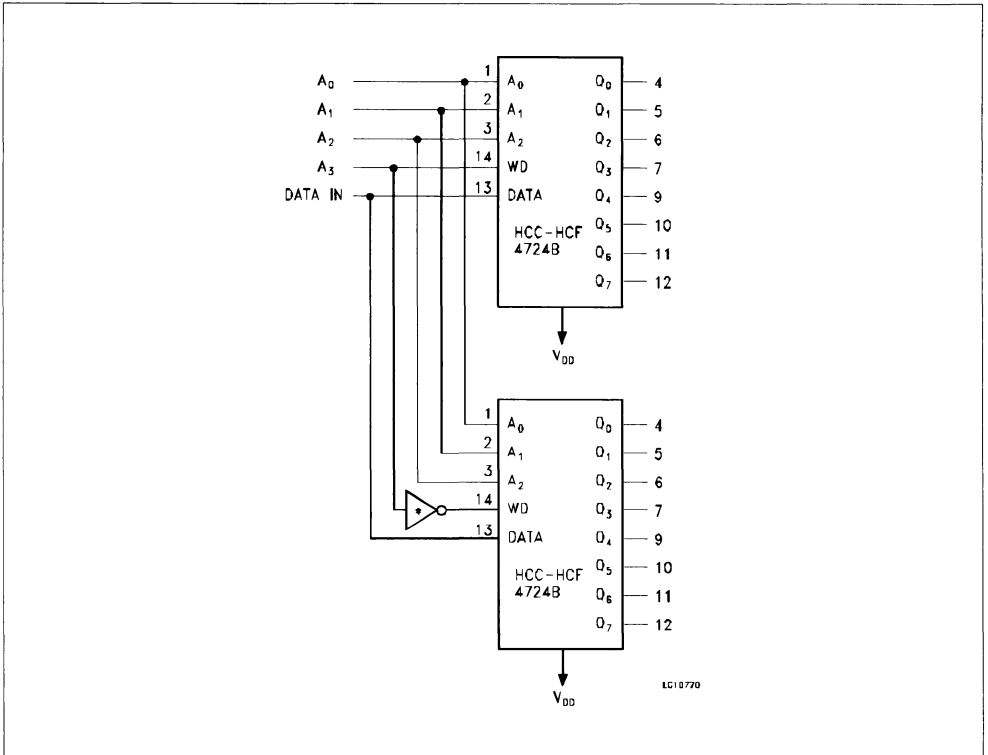
A/D Converter



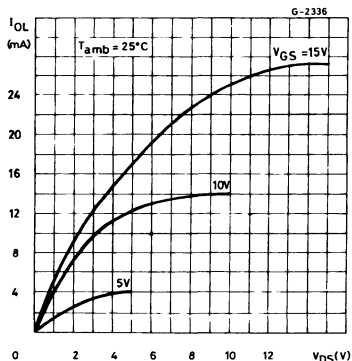
Multiple Selection Decoding - 4 x 4 Crosspoint Switch



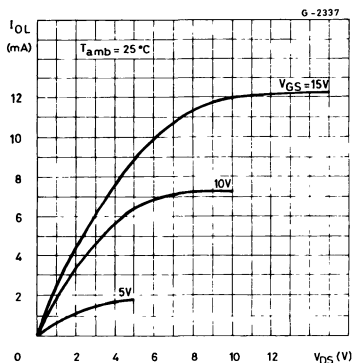
1 of 6 Decoder/Demultiplexer



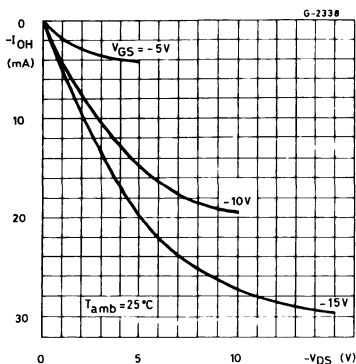
Typical Output Low (sink) Current Characteristics



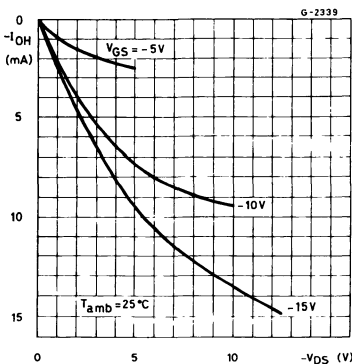
Minimum Output Low (sink) Current Characteristics



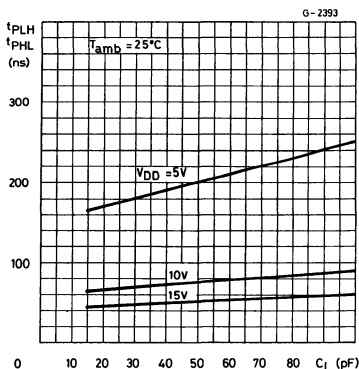
Typical Output High (source) Current Characteristics



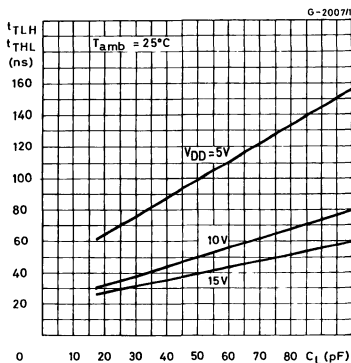
Minimum Output High (source) Current Characteristics



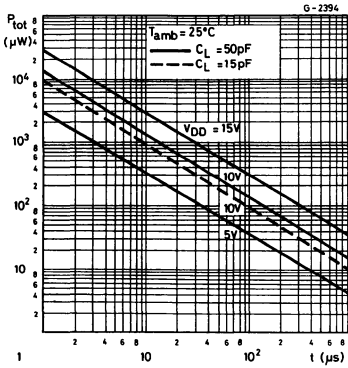
Typical Propagation Delay Time (data to Qn) vs Load Capacitance



Typical Transition Time vs Load Capacitance

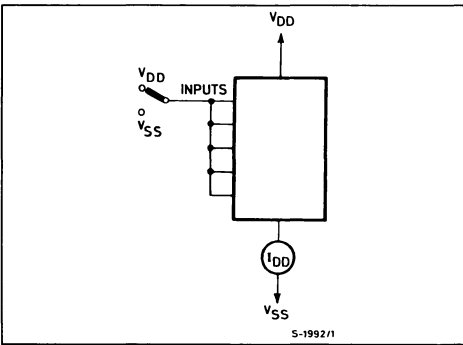


Typical Dynamic Power Dissipation vs Address Cycle Time

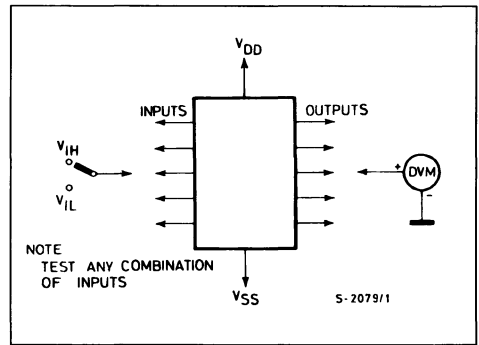


TEST CIRCUITS

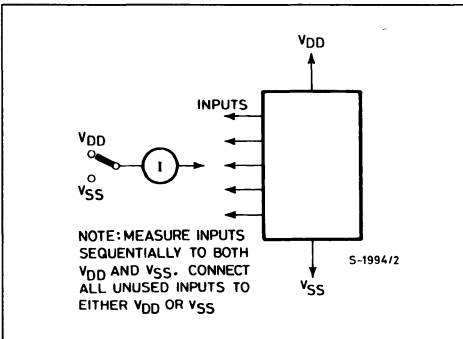
Quiescent Device Current.



Noise Immunity.



Input Leakage Current.



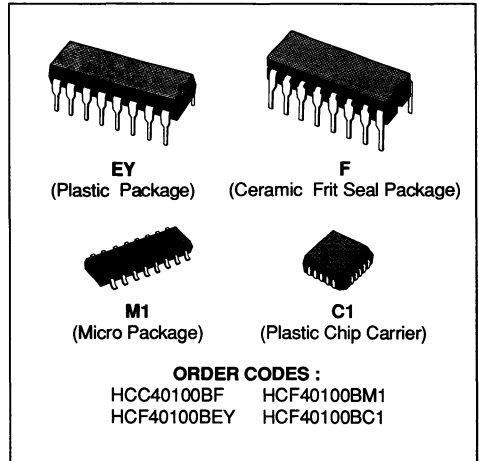
32-STAGE STATIC LEFT/RIGHT SHIFT REGISTER

- FULLY STATIC OPERATION
- SHIFT LEFT/SHIFT RIGHT CAPABILITY
- MULTIPLE PACKAGE CASCADING
- RECIRCULATE CAPABILITY
- LIFO OR FIFO CAPABILITY
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

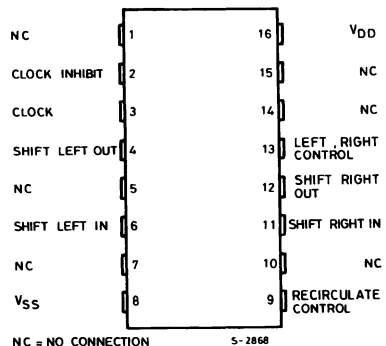
DESCRIPTION

The **HCC40100B** (extended temperature range) and **HCF40100B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF40100B** is a 32-stage shift register containing 32 D-type master-slave flip-flops. The data present at the SHIFT-RIGHT INPUT is transferred into the first register stage synchronously with the positive CLOCK edge, provided the LEFT/RIGHT CONTROL is at a low level, the RECIRCULATE CONTROL is at a high level, and the CLOCK INHIBIT is low. If the LEFT/RIGHT CONTROL is at a high level and the RECIRCULATE CONTROL is also high, data at the SHIFT-LEFT INPUT is transferred into the 32nd register stage synchronously with the positive CLOCK transition, provided the CLOCK INHIBIT is low. The state of the LEFT/RIGHT CONTROL, RECIRCULATE CONTROL, and CLOCK INHIBIT should not be changed when the CLOCK is high. Data is shifted one stage left or one stage right depending on the state of the LEFT/RIGHT CONTROL, synchronously with the positive CLOCK edge. Data clocked into the first or 32nd register states is available at the SHIFT-LEFT or SHIFT-RIGHT OUTPUT respectively, on the next negative CLOCK transition (see Data Transfer Table). No shifting occurs on the positive CLOCK edge if the CLOCK INHIBIT line is at a high level. With the

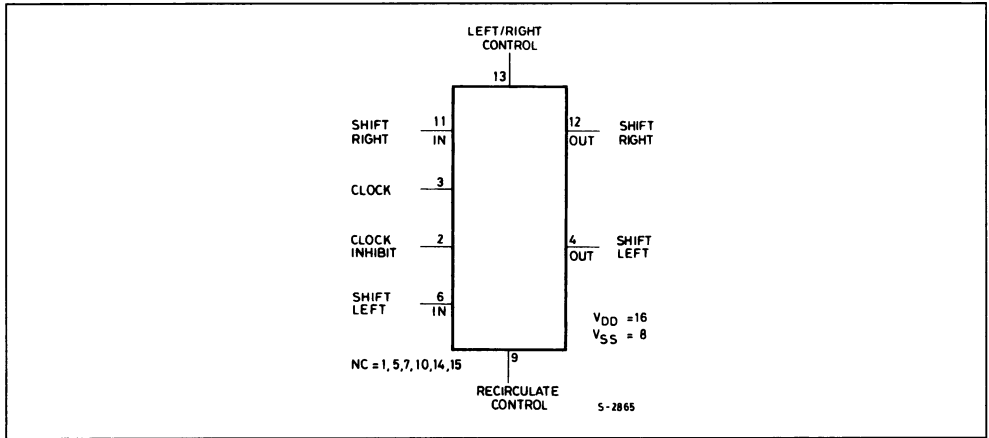
RECIRCULATE CONTROL low, data in the 32nd stage is shifted into the first stage when the LEFT/RIGHT CONTROL is low and from the 1st stage to the 32nd stage when the LEFT/RIGHT CONTROL is high.



PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

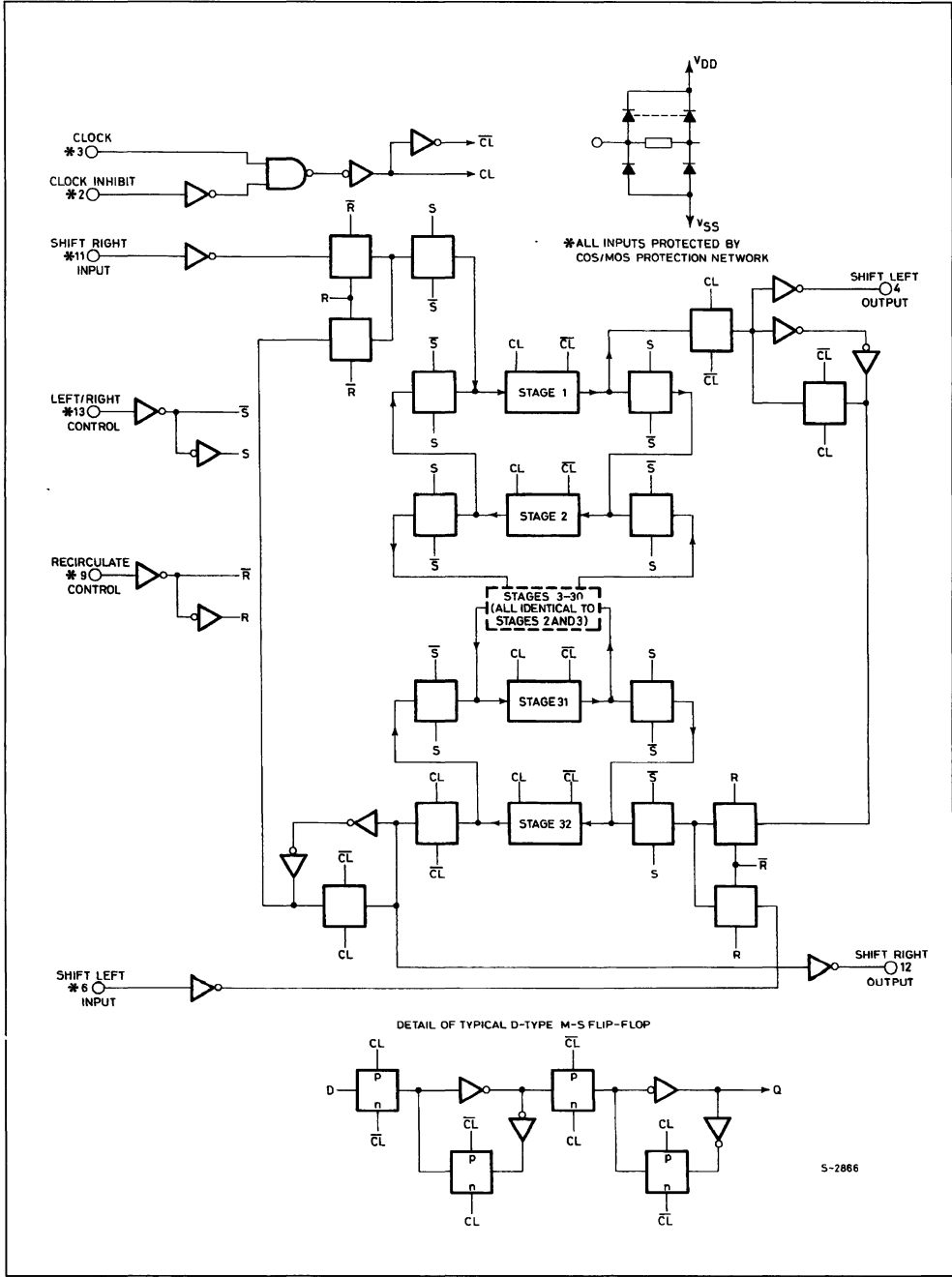
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to + 18	V
		3 to + 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLES

CONTROL

Left/Right Control	Clock · Inhibit	Recirculate Control	Action	Input Bit Origin
1	0	1	Shift Left	Shift Left Input
1	0	0	Shift Left	Stage 1
0	0	1	Shift Right	Shift Right Input
0	0	0	Shift Right	Stage 32
X	1	X	No Shift	–

DATA TRANSFER

Initial State			Clock	Resulting State	
Data Input	Clock Inhibit	Internal Stage	Level Change	Internal Stage Q	Output
0	0	X		0	NC
X	0	0		NC	0
1	0	X		1	NC
X	0	1		NC	1
X	1	1	X	NC	NC

0 = Low level 1 = High level X= Don't Care NC = No change.
 * For Shift-Right Mode For Shift-left Mode
 Data Input = SHIFT-RIGHT INPUT (Pin 11) Data input = SHIFT LEFT INPUT (Pin 6)
 Internal Stage = Stage 1 (Q1) Internal Stage = Stage 32 (Q32)
 Output = SHIFT-LEFT OUTPUT (Pin 4). Output = SHIFT-RIGHT OUTPUT (Pin 12)

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (µA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	µA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		0/20			20		100		0.08	100		3000		
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15				15		80		0.04	80		600			
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device
 * T_{High} = + 125°C for HCC device + 85°C for HCF device
 The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions				Value						Unit					
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *						
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.				
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V				
			1/9	< 1	10	7		7			7						
			1.5/13.5	< 1	15	11		11			11						
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V				
			9/1	< 1	10		3			3		3					
			13.5/1.5	< 1	15		4			4		4					
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA				
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36					
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9					
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4					
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1					
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36					
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9					
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4					
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA				
			0/10	0.5		10	1.6		1.3	2.6		0.9					
			0/15	1.5		15	4.2		3.4	6.8		2.4					
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36					
			0/10	0.5		10	1.3		1.1	2.6		0.9					
			0/15	1.5		15	3.6		3.0	6.8		2.4					
			I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵		\pm 0.1		\pm 1	μ A
					HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵		\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input					5	7.5			pF					

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is . 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min with V_{DD} = 15V

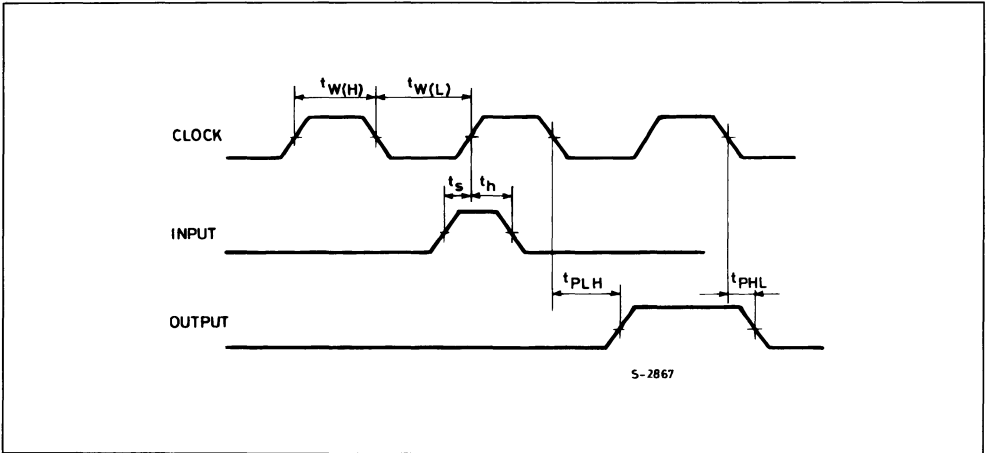
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time Clock to Shift Left/Right Output		5		360	720	ns
			10		165	330	
			15		115	230	
t _{THL} , t _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

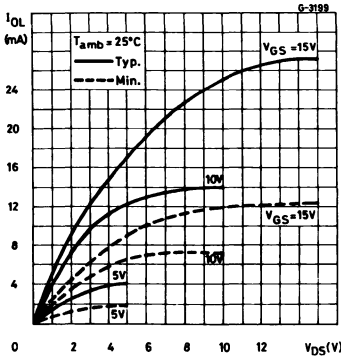
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{setup}	Data Setup Time		5	100	50		ns
			10	20	10		
			15	10	5		
t _{hold}	Data Hold Time		5	275	170		ns
			10	100	75		
			15	75	50		
t _w	Clock Input Pulse Width Low Level		5	450	225		ns
			10	230	115		
			15	190	95		
t _w	Clock Input Pulse Width High Level		5	280	140		ns
			10	150	75		
			15	140	70		
f _{CL}	Maximum Clock Input Frequency		5	1	2		MHz
			10	2.5	5		
			15	3	6		

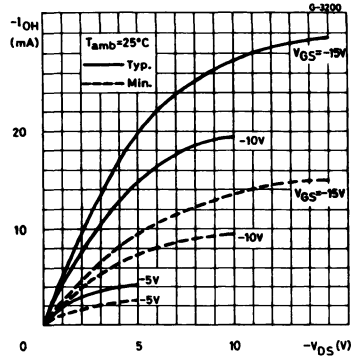
WAVEFORMS



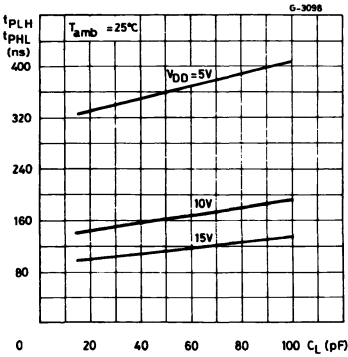
Output Low (sink) Current Characteristics.



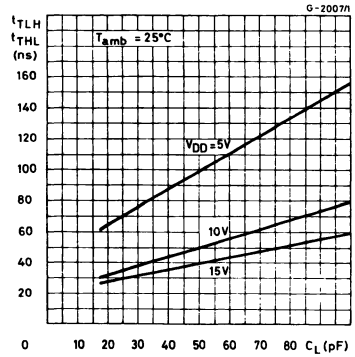
Output High (source) Current Characteristics.



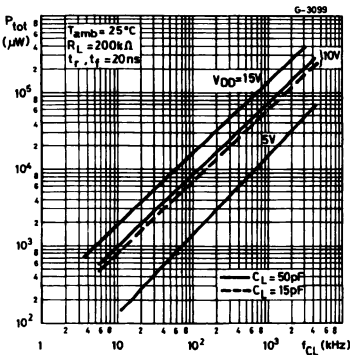
Typical Propagation Delay Time (clock to shift left right) vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

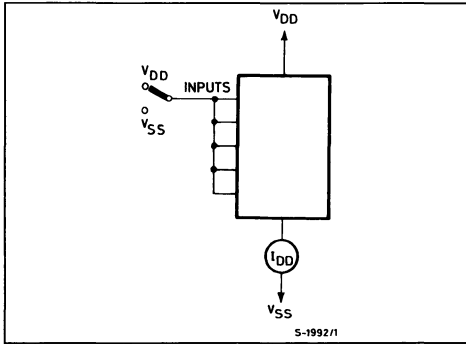


Typical Dynamic Power Dissipation vs. Clock Frequency.

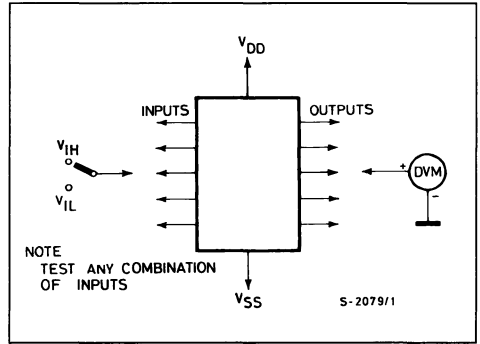


TEST CIRCUITS

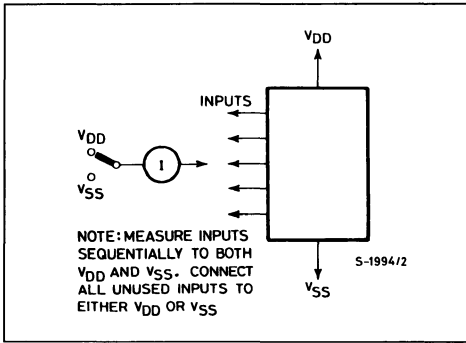
Quiescent Device Current.



Input Voltage.

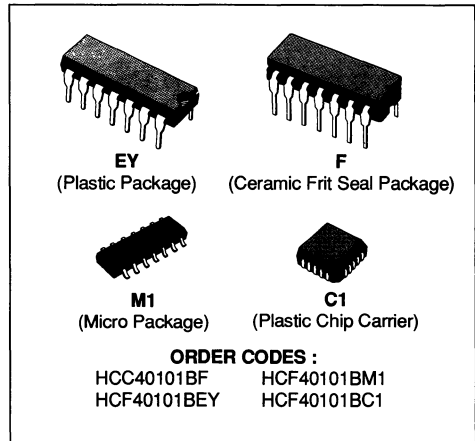


Input Leakage Current.



9-BIT PARITY GENERATOR/CHECKER

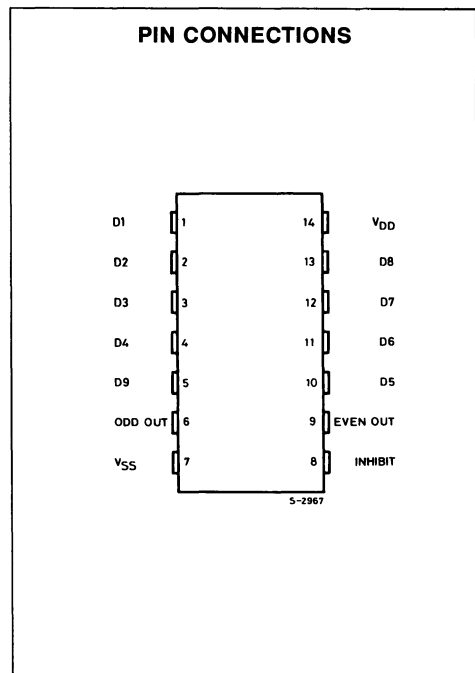
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



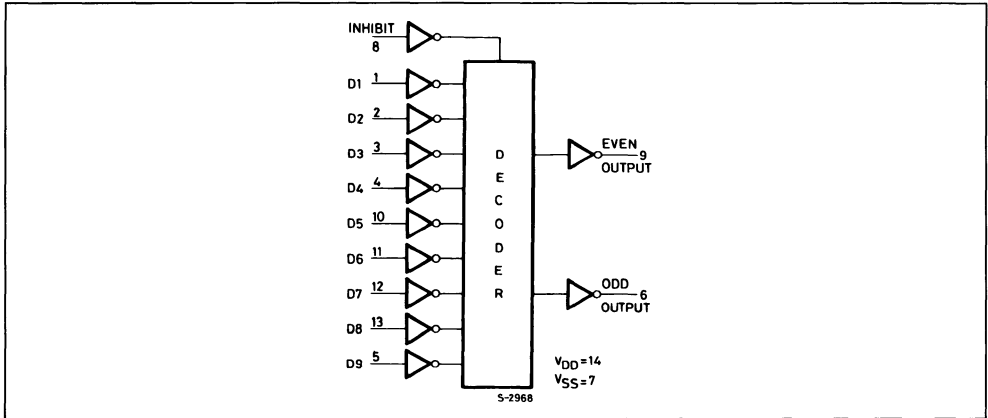
DESCRIPTION

The **HCC40101B** (extended temperature range) and **HCF40101B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF40101B** is a 9-bit (8 data bits plus 1 parity bit) parity generator/checker. It may be used to detect errors in data transmission or data retrieval. Odd and even outputs facilitate odd or even parity generation and checking. When used as a parity generator, a parity bit is supplied along with the data to generate an even or odd parity output. When used as a parity checker, the received data bits and parity bits are compared for correct parity. The even or odd outputs are used to indicate an error in the received data. Word-length capability is expandable by cascading. The **HCC/HCF40101B** is also provided with an inhibit control. If the inhibit control is set at logical "1", the even and odd outputs go to a logical "0".



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

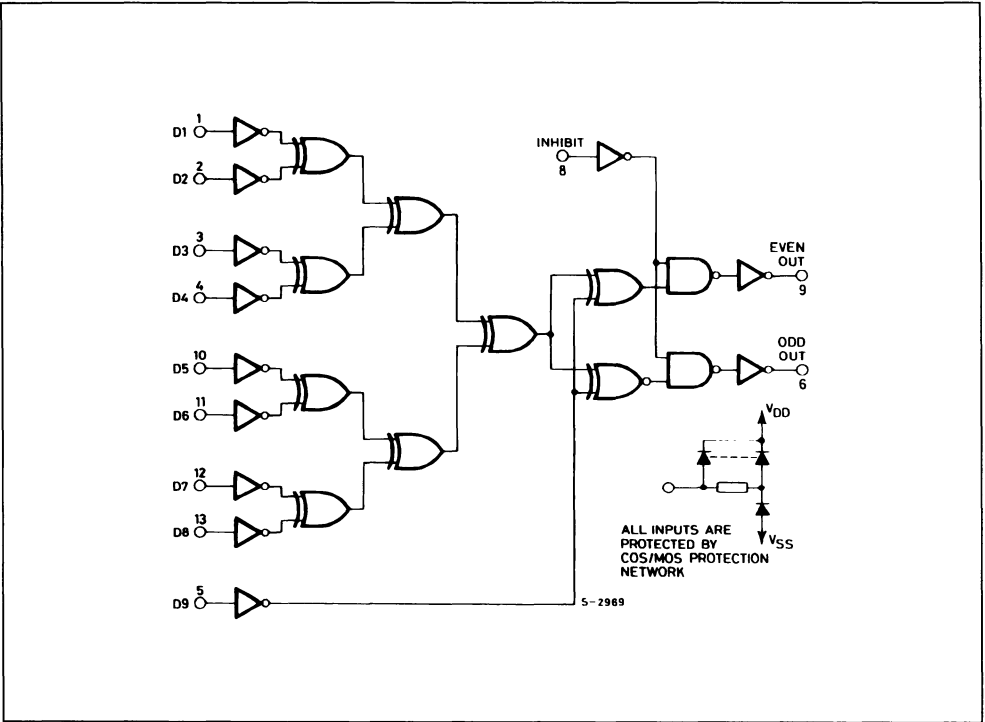
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.
 * All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

Inputs		Outputs	
D1-D9	Inhibit	Even	Odd
Σ 1's = Even	0	1	0
Σ 1's = Odd	0	0	1
X	1	0	0

X = Don't Care
 Logic 1 = High
 Logic 0 = Low.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1		
C _I	Input Capacitance		Any Input						5	7.5		pF		

* T_{Low} = -55°C for HCC device : -40°C for HCF device

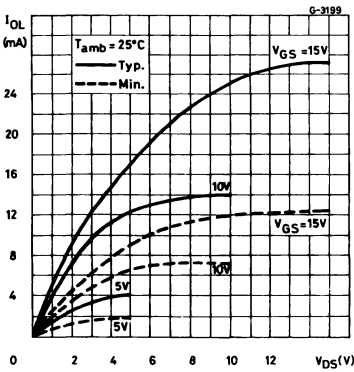
* T_{High} = +125°C for HCC device +85°C for HCF device

The Noise Margin for both "1" and "0" level is .1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V.

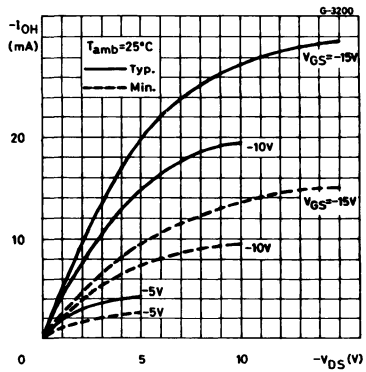
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		350	700	ns
			10		150	300	
			15		100	200	
t_{PLH} , t_{PHL}	Propagation Delay Time Inhibit to Output		5		140	280	ns
			10		70	140	
			15		50	100	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

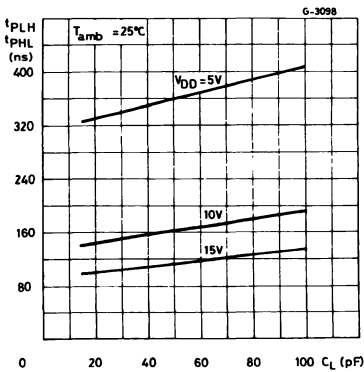
Output Low (sink) Current Characteristics.



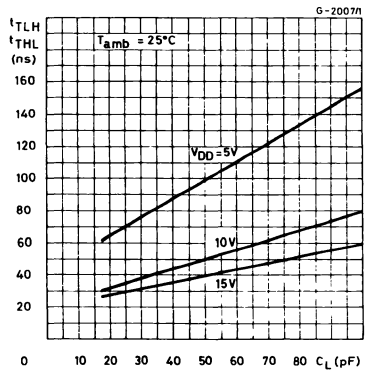
Output High (source) Current Characteristics.



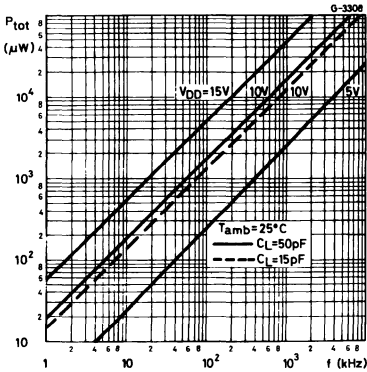
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

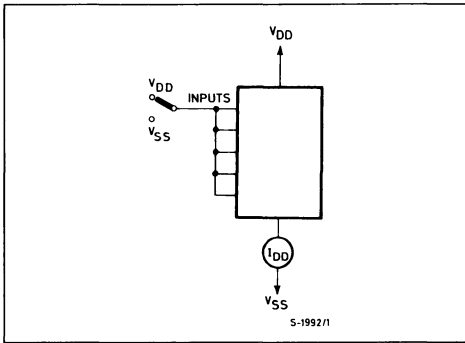


Typical Dynamic power Dissipation vs. Input Frequency.

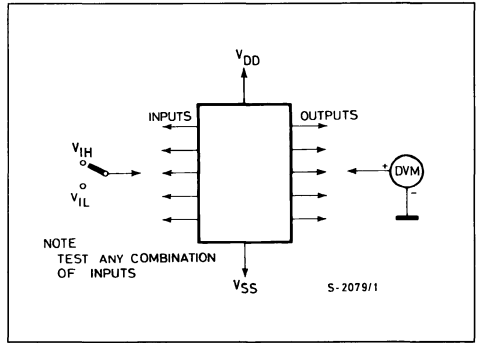


TEST CIRCUITS

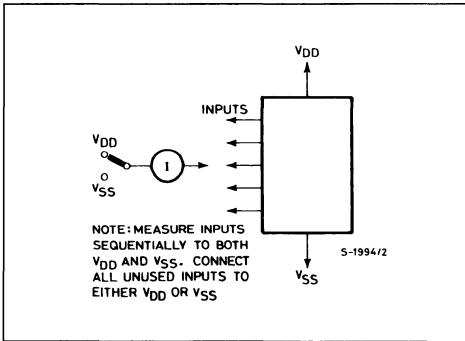
Quiescent Device Current.



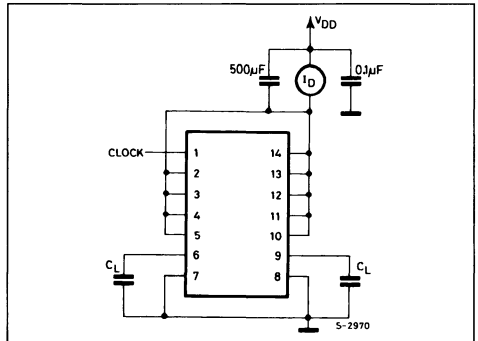
Input Voltage.



Input Leakage Current.



Dynamic Power Dissipation.



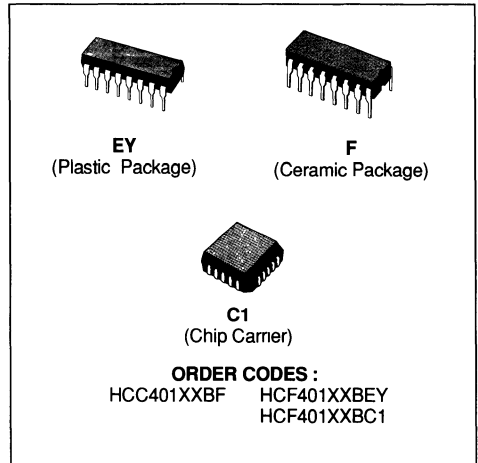
8-STAGE PRESETTABLE SYNCHRONOUS DOWN COUNTERS

40102B 2-DECADE BCD TYPE
40103B 8-BIT BINARY TYPE

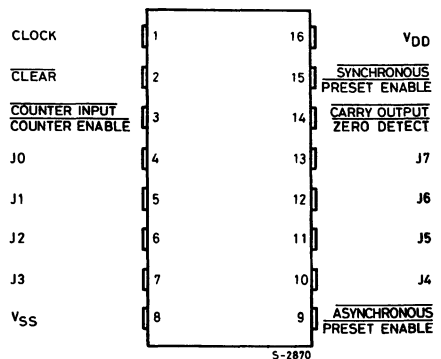
- SYNCHRONOUS OR ASYNCHRONOUS PRESET
- MEDIUM-SPEED OPERATION : $f_{CL} = 3.6\text{MHz}$ (TYP.) @ $V_{DD} = 10\text{V}$
- CASCADABLE
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13 A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC40102B**, **HCC40103B**, (extended temperature range) and the **HCF40102B**, **HCF40103B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The **HCC/HCF40102B**, and **HCC/HCF40103B** consist of an 8-stage synchronous down counter with a single output which is active when the internal count is zero. The **HCC/HCF40102B** is configured as two cascaded 4-bit BCD counters, and the **HCC/HCF40103B** contains a single 8-bit binary counter. Each type has control inputs for enabling or disabling the clock, for clearing the counter to its maximum count, and for presetting the counter either synchronously or asynchronously. All control inputs and the CARRY-OUT/ZERO-DETECT output are active-low logic. In normal operation, the counter is decremented by one count on each positive transition of the CLOCK. Counting is inhibited when the CARRY-IN/COUNTER ENABLE (CI/CE) input is high. The CARRY-OUT/ZERO-DETECT (CO/ZD) output goes low when the count reaches zero if the CI/CE input is low, and remains low for one full clock period. When the SYNCHRONOUS PRESET-ENABLE (SPE) input is low, data at the JAM input is clocked into the counter on the next positive clock transition regardless of the state of the CI/CE input. When the ASYNCHRONOUS PRESET-ENABLE (APE) input is low, data at the



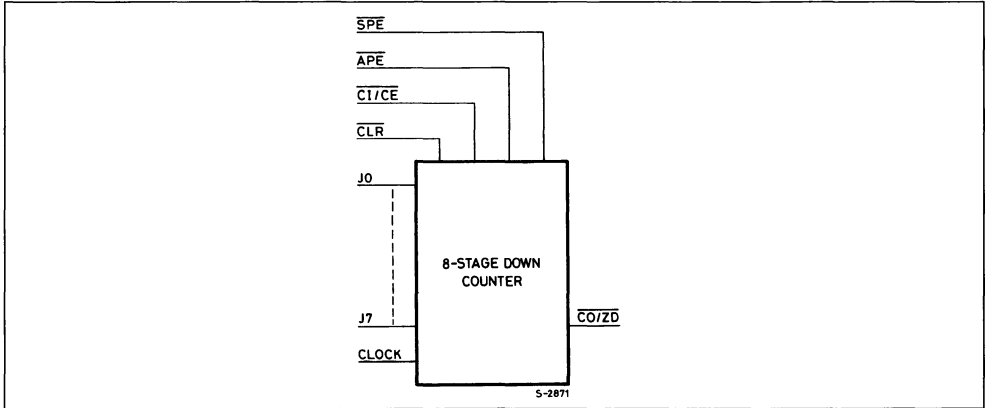
PIN CONNECTIONS



JAM inputs is asynchronously forced into the counter regardless of the state of the SPE, CI/CE, or CLOCK inputs. JAM inputs JO-J7 represent two 4-bit BCD words for the HCC/HCF40102B and a single 8-bit binary word for the HCC/HCF40103B. When the CLEAR (CLR) input is low, the counter is asynchronously cleared to its maximum count (99₁₀ for the HCC/HCF40102B and 255₁₀ for

theHCC/HCF40103B) regardless of the state of any other input. The precedence relationship between control input is indicated in the truth table. If all control inputs are high at the time of zero count, the counters will jump to the maximum count, giving a counting sequence of 100 or 256 clock pulses long. The HCC/HCF40102B and HCC/HCF40103B may be cascaded using the CI/CE input and the

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

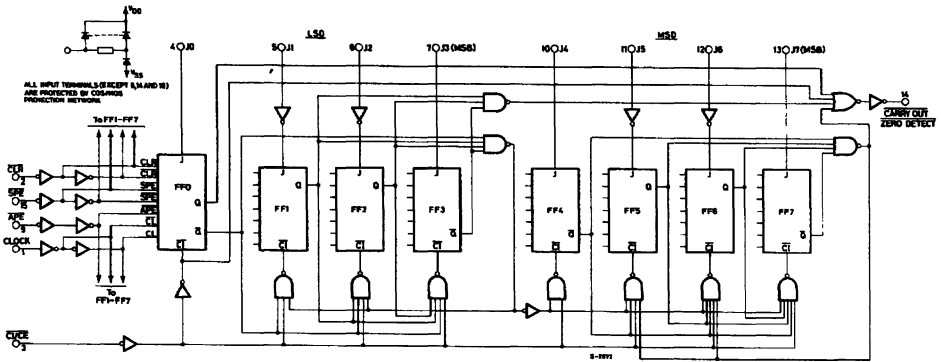
* All voltages are with respect to V_{SS} (GND)

RECOMMENDED OPERATING CONDITIONS

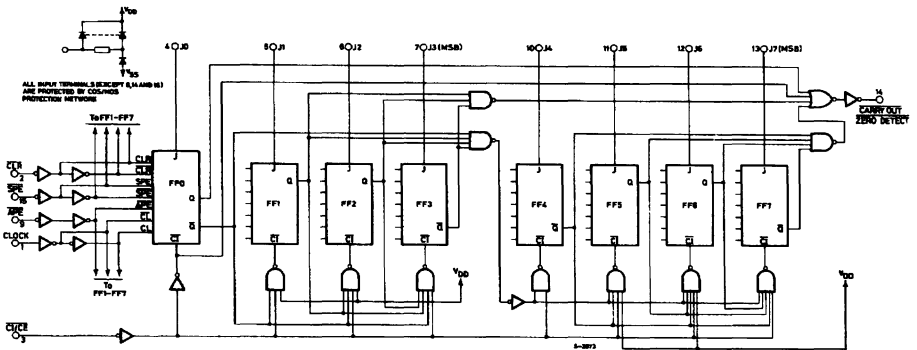
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS

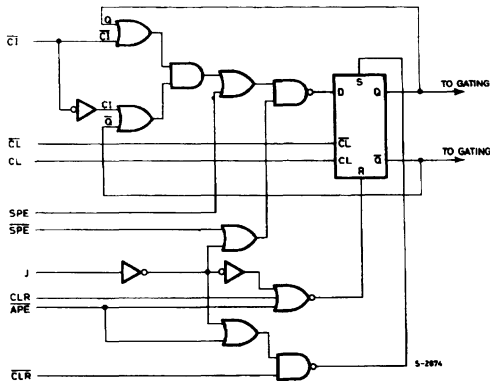
40102B



40103B

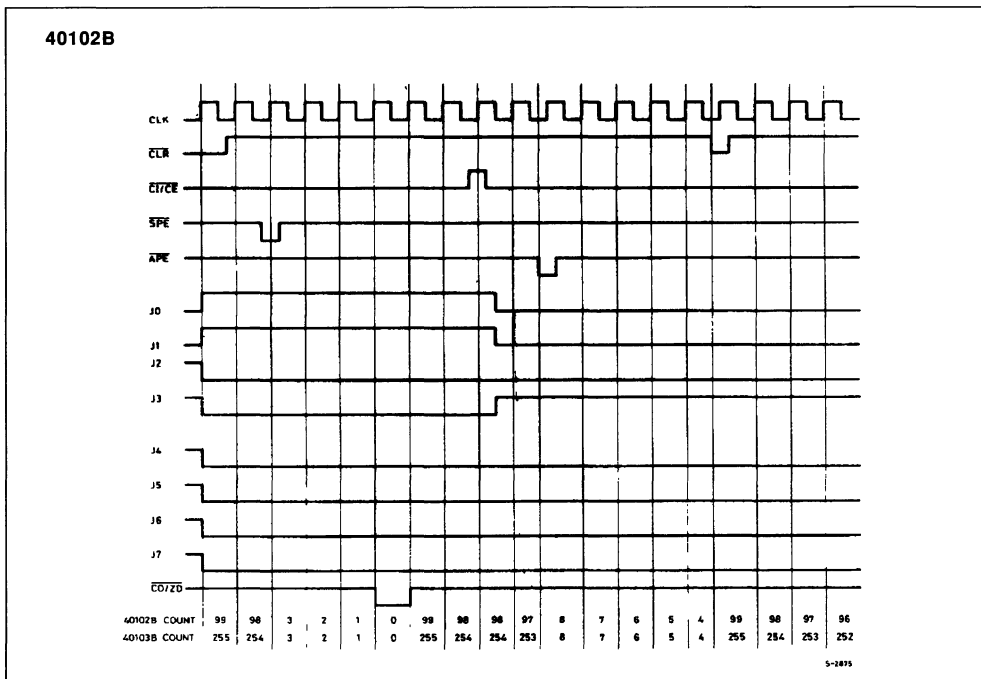


Detail logic diagram for flip-flops, FF0-FF7 used in logic diagrams for 40102B and 40103B.



LOGIC DIAGRAMS (continued)

Timing Diagram for 40102B and 40103B



TRUTH TABLE

Control Inputs				Preset Mode	Action
CLR	APE	SPE	CI/CE		
1	1	1	1	Synchronous	Inhibit Counter
1	1	1	0		Count Down
1	1	0	X		Preset on Next Positive Clock Transition
1	0	X	X	Asynchronous	Preset Asynchronously
0	X	X	X		Clear to Maximum Count

- Notes :
- 0 = Low level
1 = High level
X = Don't care
 - Clock connected to clock input.
 - Synchronous operation changes occur on negative-to-positive clock transitions.
JAM inputs : HCC/HCF010B ; MSD = J7, J6, J5, J4 (J7 is MSB)
LSD = J3, J2, J1, J0 (J3 is MSB)
HCC/HCF40103B Binary ; MSB = J7, LSB = J0

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

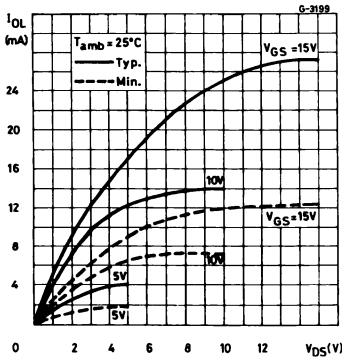
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
	HCF Types	0/ 5			5		20		0.04	20		150		
		0/10			10		40		0.04	40		300		
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
			0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15											
C _I	Input Capacitance			Any Input					5	7.5			μ F	

* T_{Low}= - 55°C for HCC device ; - 40°C for HCF device.* T_{High}= + 125°C for HCC device ; + 85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

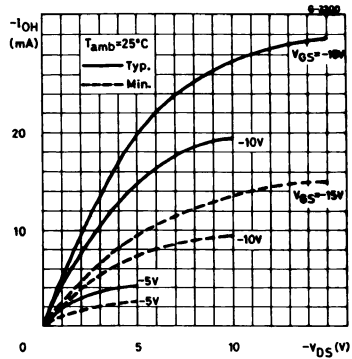
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter		Test Conditions		Value			Unit
			V_{DD} (V)		Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time	Clock to-out	5		300	600	ns	
			10		130	260		
			15		95	190		
		Carry In/Counter Enable-to-output	5		200	400	ns	
			10		90	180		
			15		65	130		
		Asynchronous Preset Enable-to-output	5		650	1300		
			10		300	600		
			15		200	400		
		$\overline{\text{Clear}}$ -to-output	5		375	750	ns	
			10		180	360		
			15		100	200		
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns	
			10		50	100		
			15		40	80		
t_w	Pulse Width	Clock Pulse Width	5	300	150	ns		
			10	180	90			
			15	80	40			
		$\overline{\text{CLR}}$ Pulse Width	5	320	160	ns		
			10	160	80			
			15	100	50			
		$\overline{\text{APE}}$ Pulse Width	5	360	180	ns		
			10	160	80			
			15	120	60			
t_{setup}	Setup Time	SPE Setup Time	5	280	140	ns		
			10	140	70			
			15	100	50			
		JAM Setup Time	5	200	100	ns		
			10	80	40			
			15	60	30			
f_{CL}	Maximum Clock Input Frequency		5	0.7	1.4	MHz		
			10	1.8	3.6			
			15	2.4	4.8			

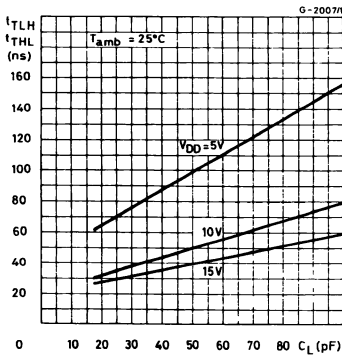
Output Low (sink) Current Characteristics.



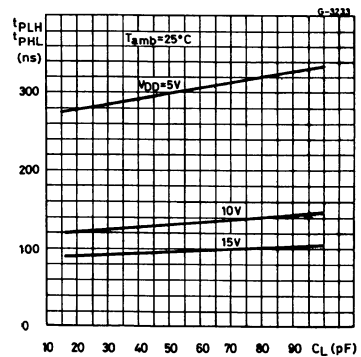
Output High (source) Current Characteristics.



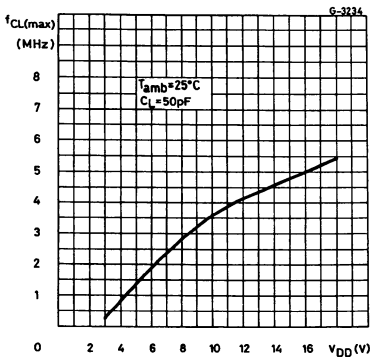
Typical Transition Time vs. Load Capacitance.



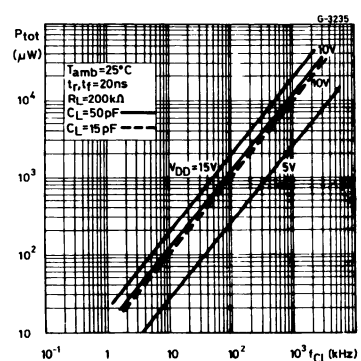
Typical Propagation Delay Time vs. Load Capacitance (clock to CO/ZD).



Typical Maximum Clock Input Frequency vs. Supply Voltage.

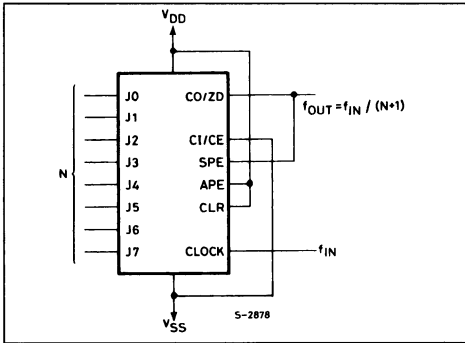


Typical Dynamic Power Dissipation vs. Frequency.

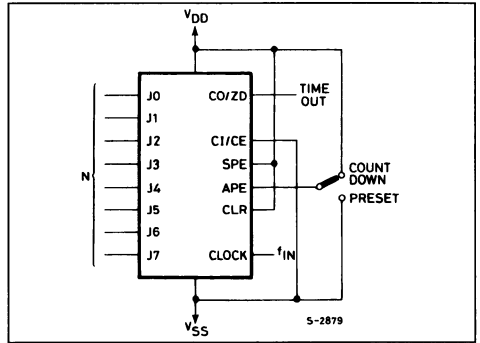


TYPICAL APPLICATIONS

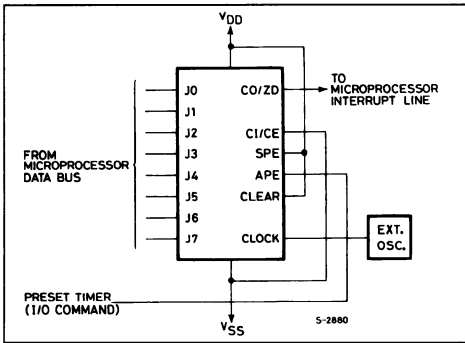
Divide-by-"N" Counter.



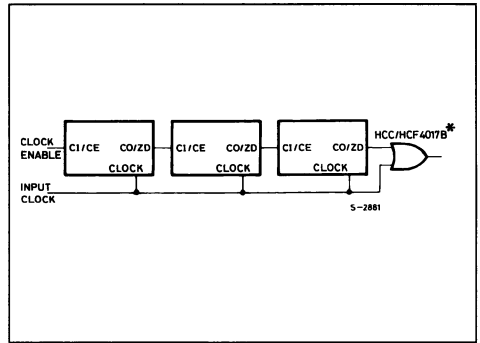
Programmable Timer.



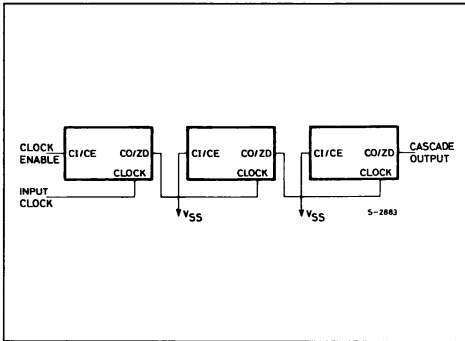
Microprocessor Interrupt Timer.



Synchronous Cascading.



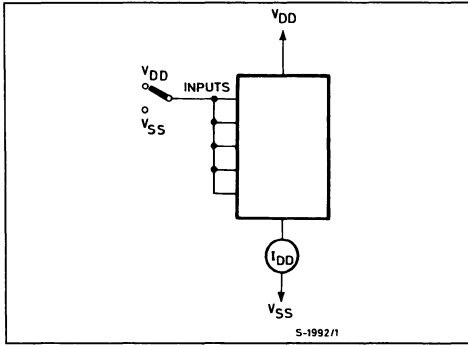
Microprocessor Interrupt Timer.



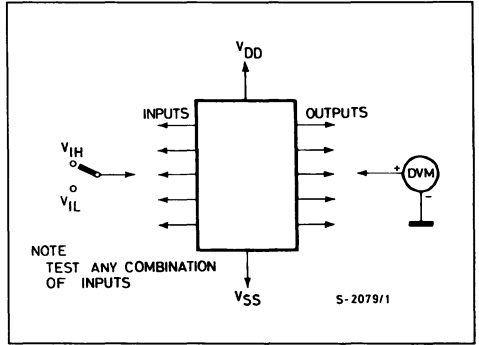
* An output spike (160ns @ $V_{DD} = 5V$) occurs whenever two or more devices are cascaded in the parallel-clocked mode because the clock-to-carry out delay is greater than the carry-in-to-carry out delay. This spike is eliminated by gating the out carry of the last device with the clock as shown.

TEST CIRCUITS

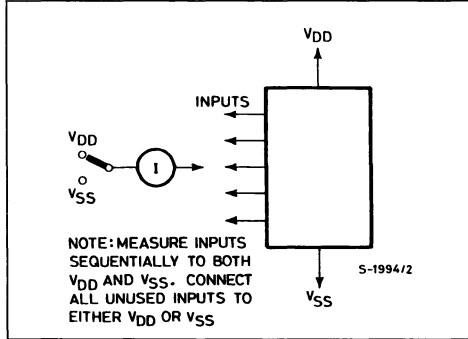
Quiescent Device Current.



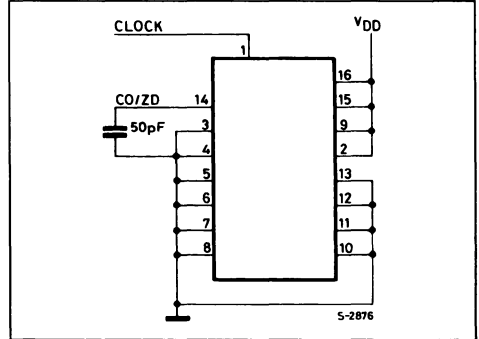
Input Voltage.



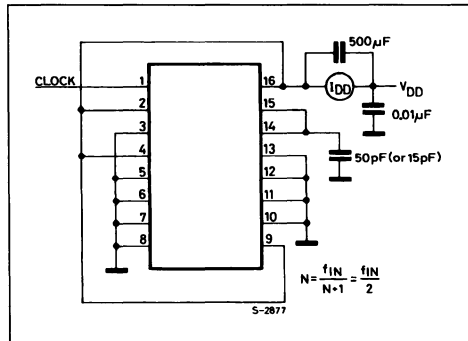
Input Current.



Maximum Clock Frequency.

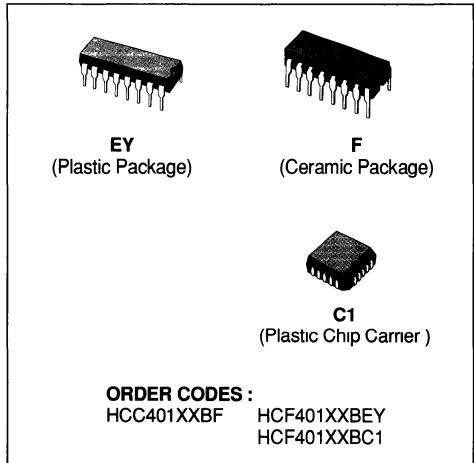


Dynamic Power Dissipation.



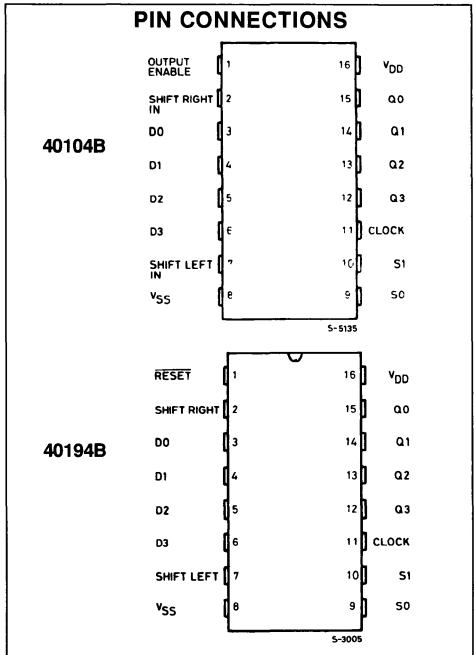
4-BIT BIDIRECTIONAL UNIVERSAL SHIFT REGISTER

- MEDIUM-SPEED OPERATION : $f_{CL} = 9\text{MHz}$ (typ.) @ $V_{DD} = 10\text{V}$
- FULLY STATIC OPERATION
- SYNCHRONOUS PARALLEL OR SERIAL OPERATION
- THREE-STATE OUTPUTS (**HCC/HCF40104B**)
- ASYNCHRONOUS MASTER RESET (**HCC/HCF40194B**)
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

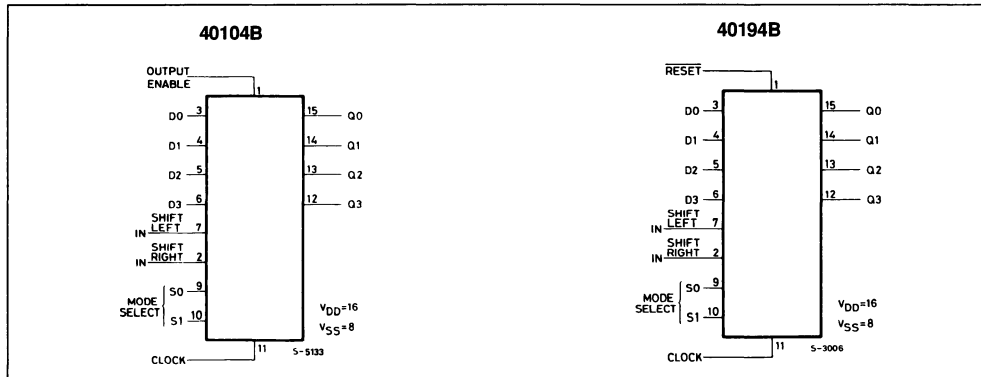
The **HCC40104B**, **HCC40194B**, (extended temperature range) and the **HCC40104B**, **HCF40194B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF 40104B** is a universal shift register featuring parallel inputs, parallel outputs, SHIFT RIGHT and SHIFT LEFT serial inputs, and a high-impedance third output state allowing the device to be used in bus-organized systems. In the parallel-load mode (S_0 and S_1 are high), data is loaded into the associated flip-flop and appears at the output after the positive transition of the CLOCK input. During loading, serial data flow is inhibited. Shift-right and shift-left are accomplished synchronously on the positive clock edge with serial data entered at the SHIFT RIGHT and SHIFT LEFT serial inputs, respectively. Clearing the register is accomplished by setting both mode controls low and clocking the register. When the output enable input is low, all outputs assume the high impedance state. The **HCC/HCF40194B** is a universal shift register featuring parallel inputs, parallel outputs SHIFT RIGHT and SHIFT LEFT serial inputs, and a direct overriding clear input. In the parallel-load mode (S_0 and S_1 are high), data is loaded into the associated



flip-flop and appears at the output after the positive transition of the CLOCK input. During loading, serial data flow is inhibited. Shift right and shift left are accomplished synchronously on the positive clock edge with data entered at the SHIFT RIGHT and SHIFT

LEFT serial inputs, respectively. Clocking of the register is inhibited when both mode control inputs are low. When low, the RESET input resets all stages and forces all outputs low. The HCC/HCF40194B is similar to industry types 340194 and MC40194.

FUNCTIONAL DIAGRAMS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

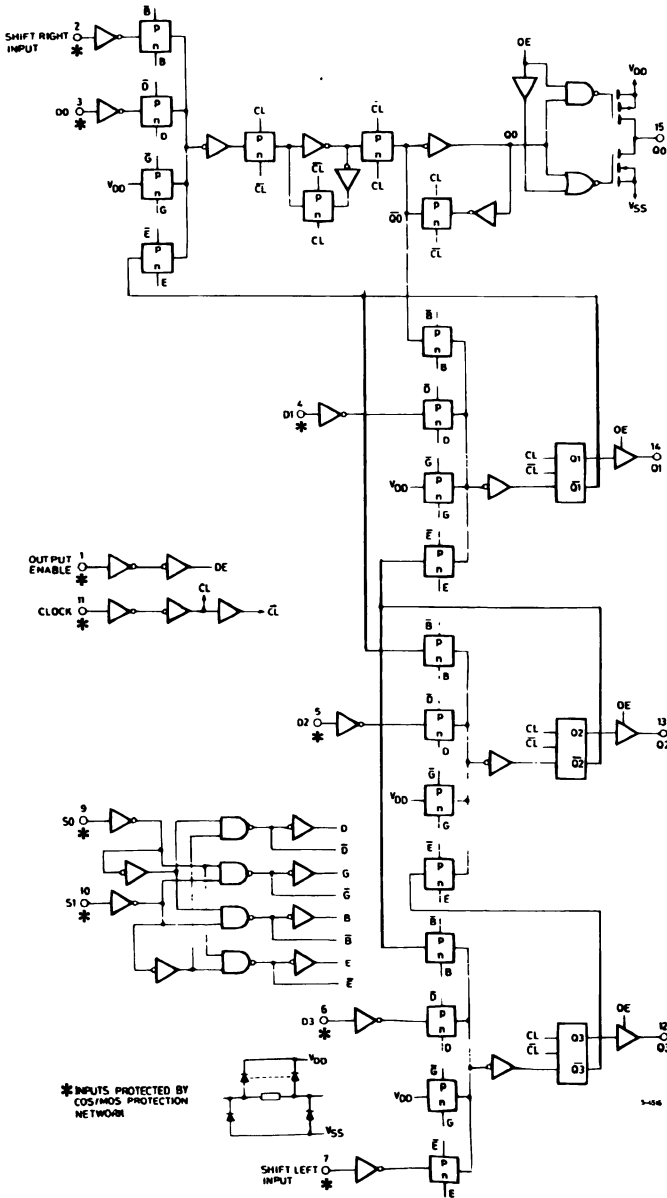
* All voltages values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

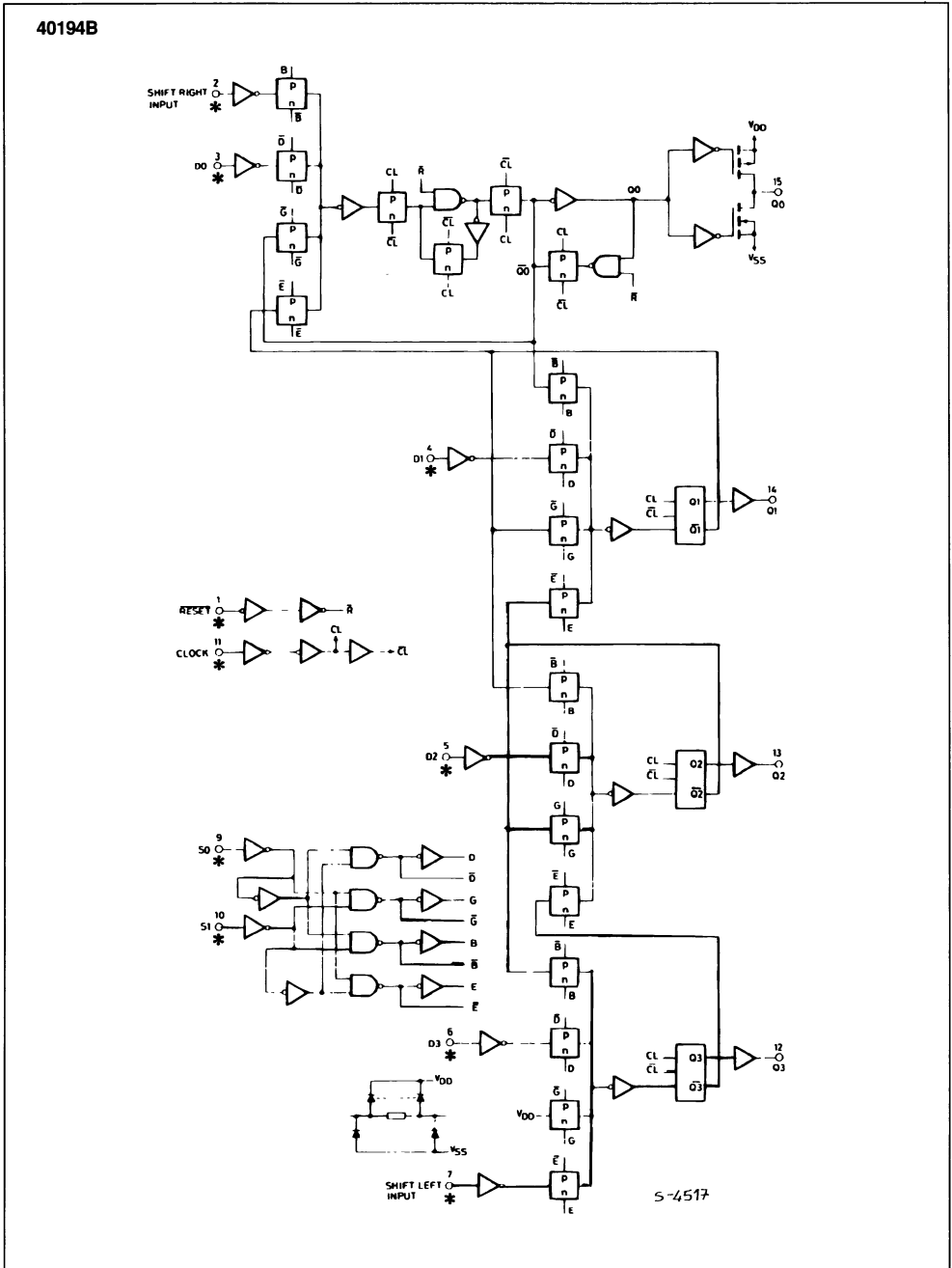
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

LOGIC DIAGRAMS

40104B



LOGIC DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{LOW} = -55°C for HCC device ; -40°C for HCF device.* T_{HIGH} = +125°C for HCC device ; +85°C for HCF device.The noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 min. with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH}, t_{PHL}	Propagation Delay Time Clock to Q		5		220	440	ns
			10		100	200	
			15		70	140	
$t_{PZH}, t_{PZL},$ t_{PLZ}	3-state Outputs ■ High Impedance		5		80	160	ns
			10		35	70	
			15		25	50	
t_{PHZ}			5		45	90	ns
			10		25	50	
			15		20	40	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Setup Time D0,D3,SR, SL to Clock		5		80	100	ns
			10		35	70	
			15		20	50	
	S0, S1 to Clock		5		200	400	ns
			10		110	220	
			15		65	130	
t_{hold}	Hold Time D0,D3,SR, SL to Clock		5		- 65	0	ns
			10		- 25	0	
			15		- 15	0	
	S0, S1 to Clock		5		- 170	0	ns
			10		- 95	0	
			15		- 55	0	
t_w	Clock Pulse Width		5		90	180	ns
			10		40	180	
			15		25	50	
f_{CL}	Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8	15		
t_r, t_f	Clock Input Rise or Fall Time		5			1000	μs
			10			100	
			15			100	
t_w	Reset Pulse Width*		5		150	300	ns
			10		100	200	
			15		70	140	
t_{PRHL}	Propagation Delay Reset*		5		230	460	ns
			10		90	180	
			15		65	130	

■ For 40104B series only * For 40194B series only.

TRUTH TABLES

40104B

Clock Δ	Mode Select		Output Enable	Action
	S0	S1		
	0	0	1	Reset
	1	0	1	Shift Right (Q0 toward Q3)
	0	1	1	Shift Left (Q3 toward Q0)
	1	1	1	Parallel Load
X	X	X	0	Operations occur as shown above, but outputs assume high impedance

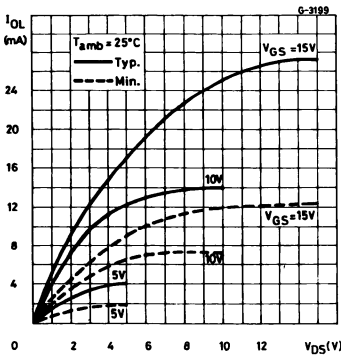
40194B

Clock	Mode Select		Reset	Action
	S0	S1		
X	0	\checkmark	1	No Change
	1	0	1	Shift Right (Q0 toward Q3)
	0	1	1	Shift Left (Q3 toward Q0)
	1	1	1	Parallel Load
X	X	X	0	Reset

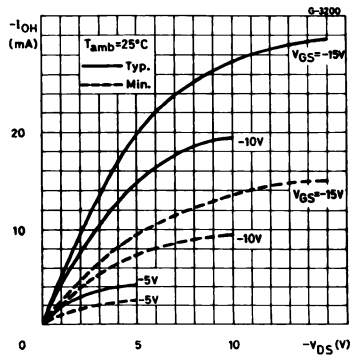
1=High level
0=Low level

X= Don't care
 Δ = Level change

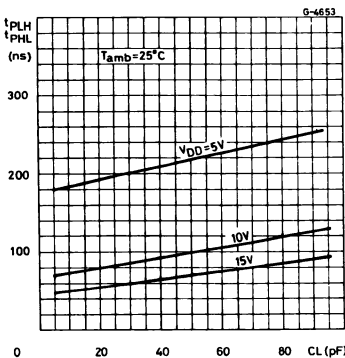
Output Low (sink) Current Characteristics.



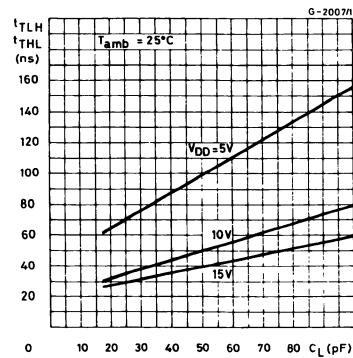
Output High (source) Current Characteristics.



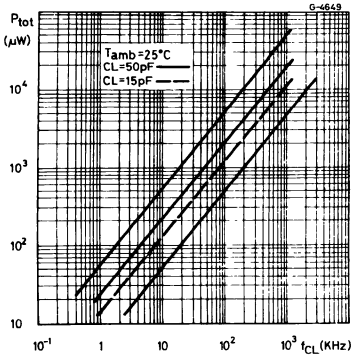
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

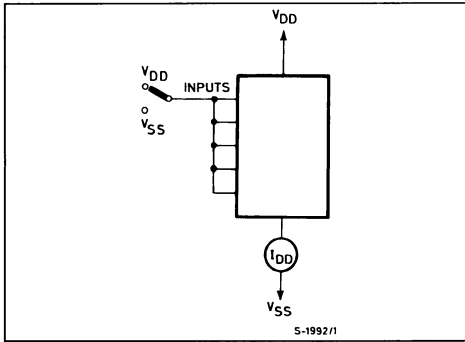


Typical Dynamic Power Dissipation vs. Frequency.

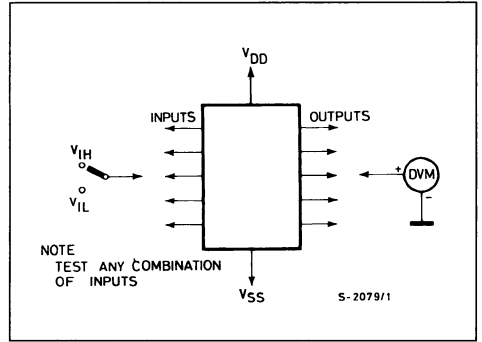


TEST CIRCUITS

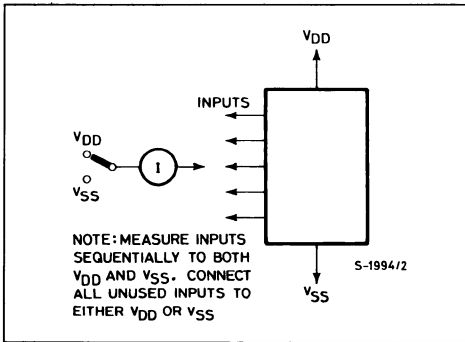
Quiescent Device Current.



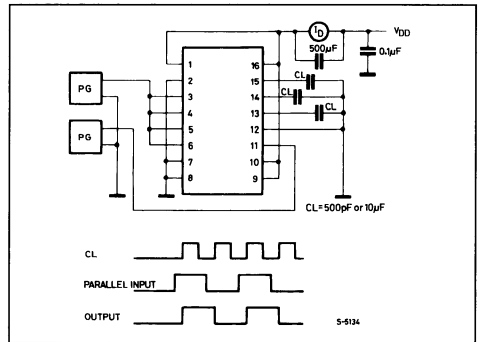
Input Voltage.



Input Leakage Current.



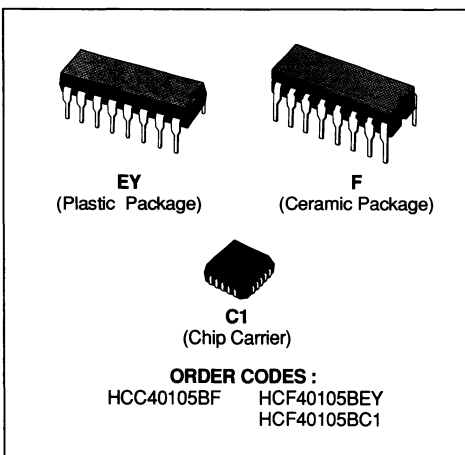
Dynamic Power Dissipation.



FIFO REGISTER

- INDEPENDENT ASYNCHRONOUS INPUTS AND OUTPUTS
- 3-STATE OUTPUTS
- EXPANDABLE IN EITHER DIRECTION
- STATUS INDICATORS ON INPUT AND OUTPUT
- RESET CAPABILITY
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

READY) indicates if the FIFO contains data. As the earliest data are removed from the bottom of the data stack (the output end), all data entered later will automatically propagate (ripple) toward the output.

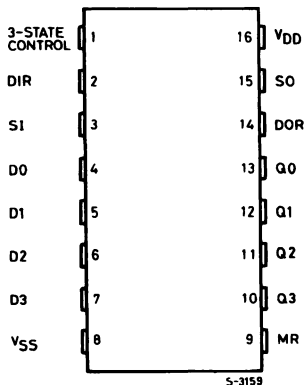


DESCRIPTION

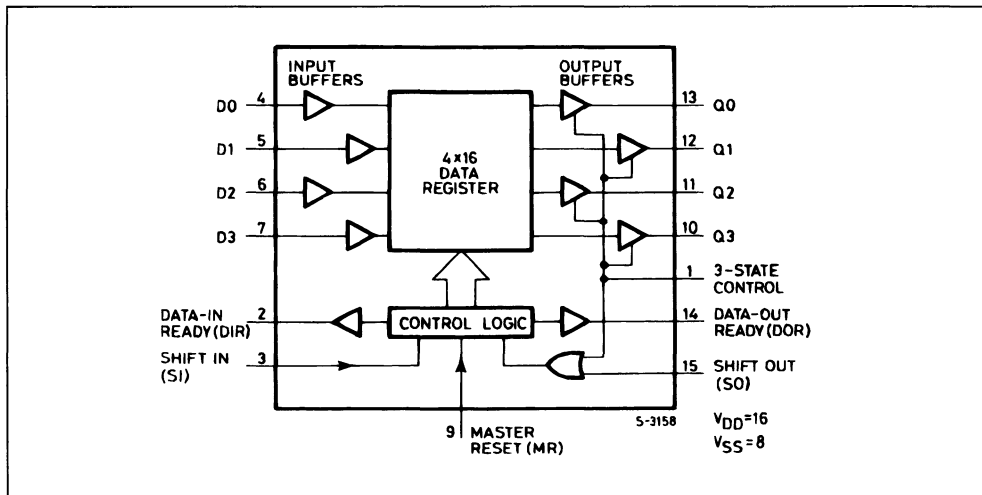
The **HCC40105B** (extended temperature range) and **HCF40105B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package.

The **HCC/HCF40105B** is a low-power first-in-first-out (FIFO) "elastic" storage register that can store 16 4-bit words. It is capable of handling input and output data at different shifting rates. This feature makes it particularly useful as a buffer between asynchronous systems. Each word position in the register is clocked by a control flip-flop, which stores a marker bit. A "1" signifies that the position's data is filled and a "0" denotes a vacancy in that position. The control flip-flop detects the state of the preceding flip-flop and communicates its own status to the succeeding flip-flop. When a control flip-flop is in the "0" state and sees a "1" in the preceding flip-flop, it generates a clock pulse that transfers data from the preceding four data latches into its own four data latches and resets the preceding flip-flop to "0". The first and last control flip-flops have buffered outputs. Since all empty locations "bubble" automatically to the input end, and all valid data ripple through to the output end, the status of the first control flip-flop (DATA-IN READY) indicates if the FIFO is full, and the status of the last flip-flop (DATA-OUT

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

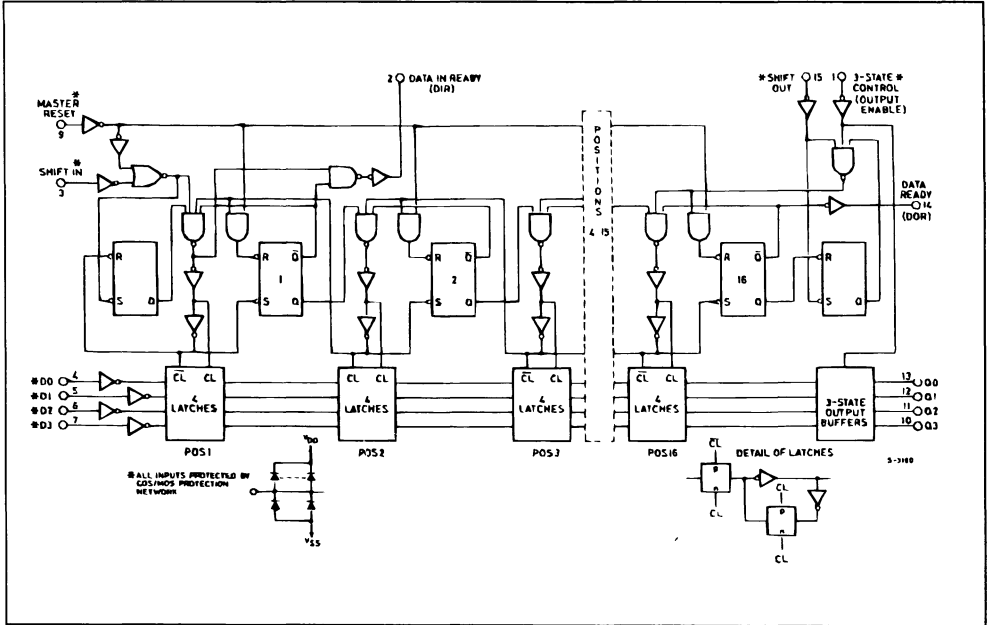
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

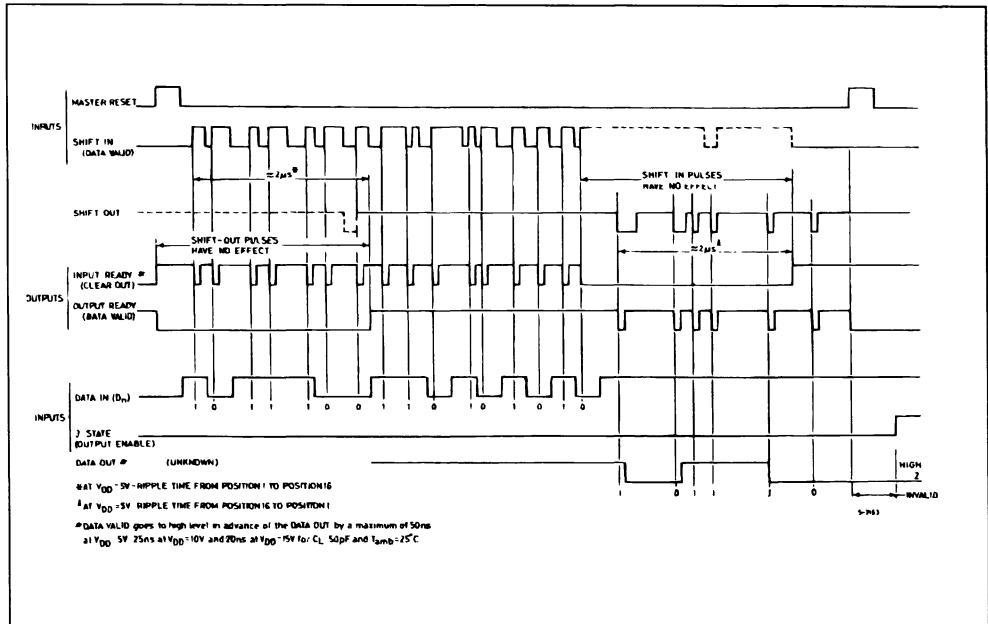
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



TIMING DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
		HCF Types	0/20			20		100		0.08	100		3000	
			0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
0/15			15		80		0.04	80		600				
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
		0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
0/10	9.5			10	-1.3		-1.1	-2.6		-0.9				
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15	Any Input		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
I _{OH} , I _{OL} **	3-State Output Leakage Current	HCC Types	0/18	0/18		18		± 0.4		$\pm 10^{-4}$	± 0.4		± 12	μ A
		HCF Types	0/15	0/15		15		± 1.0		$\pm 10^{-4}$	± 1.0		± 7.5	
C _I	Input Capacitance		Any Input						5	7.5			pF	

*T_{Low} = -55°C for HCC device ; -40°C for HCF device*T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

* * Forced output disable.

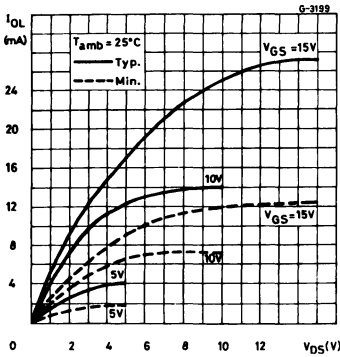
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ }^{\circ}\text{C}$, all input rise and fall time = 20 ns)

Symbol	Parameter	Test Conditions	Value			Unit	
			V_{DD} (V)	Min.	Typ.		Max.
t_{PHL}	Propagation Delay Time Shift-out or Reset to Data-out Ready		5		185	370	ns
			10		90	180	
			15		65	130	
t_{PHL}	Propagation Delay Time Shift-in to Data-in Ready		5		160	320	ns
			10		65	130	
			15		45	90	
t_{PZH}, t_{PZL}	Propagation Delay Time 3-state Control to Data-out		5		140	280	ns
			10		60	120	
			15		40	80	
t_{PHZ}, t_{PLZ}	Propagation Delay Time 3-State Control to Data-out		5		100	200	ns
			10		50	100	
			15		40	80	
t_{PLH}	Ripple-through Delay Input to Output		5		2	4	μs
			10		1	2	
			15		0.7	1.4	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
f_i	Shift-in or Shift-out Rate		5		1.5	3	MHz
			10		3	6	
			15		4	8	
t_{WH}	Shift-in Pulse Width		5	200	100		ns
			10	80	40		
			15	60	30		
t_{WL}	Shift-out Pulse Width		5	360	180		ns
			10	160	80		
			15	100	50		
t_r	Shift-in or Shift-out Rise Time		5			15	μs
			10			15	
			15			15	
t_f	Shift-in Fall Time		5			15	μs
			10			15	
			15			15	
t_f	Shift-out Fall Time		5			15	μs
			10			5	
			15			5	
t_{setup}	Data Setup Time		5	0			ns
			10	0			
			15	0			

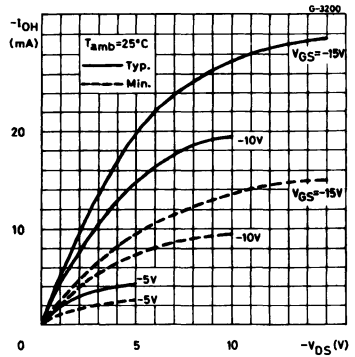
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)	Min.	Typ.	Max.		
t_{hold}	Data Hold Time	5	350	175		ns	
		10	150	75			
		15	120	60			
t_{WL}	Data-in Ready Pulse Width	5		260	520	ns	
		10		100	120		
		15		70	140		
t_{WL}	Data-out Ready Pulse Width	5		220	440	ns	
		10		90	180		
		15		665	130		
t_{WH}	Master Reset Pulse Width	5	200	100		ns	
		10	90	45			
		15	60	30			

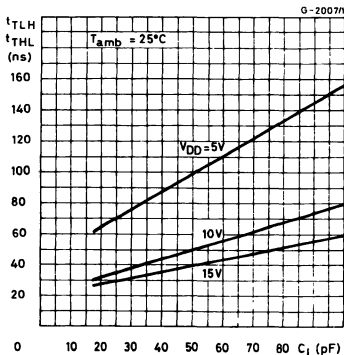
Output Low (sink) Current Characteristics.



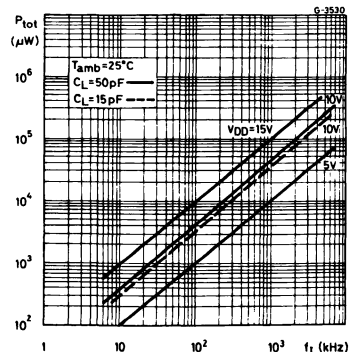
Output High (source) Current Characteristics.



Typical Transition Time vs. Load Capacitance.

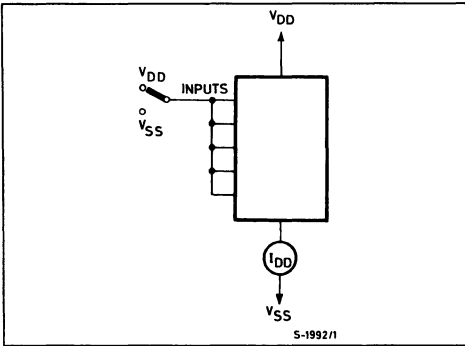


Typical Dynamic Power Dissipation vs. Frequency.

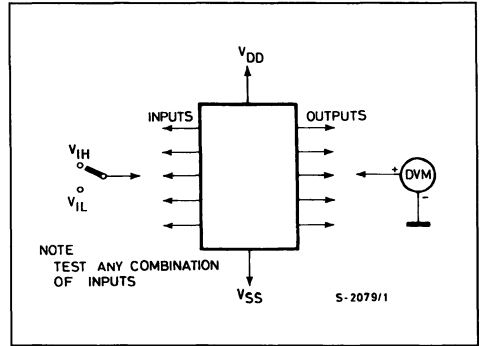


TEST CIRCUITS

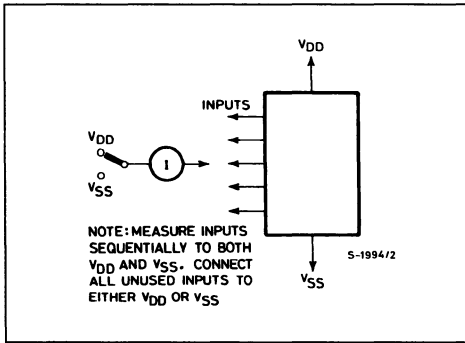
Quiescent Device Current.



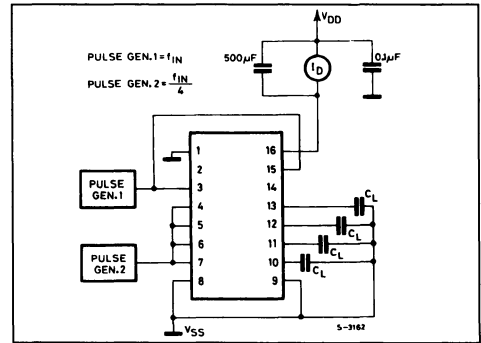
Input Voltage.



Input Leakage Current.

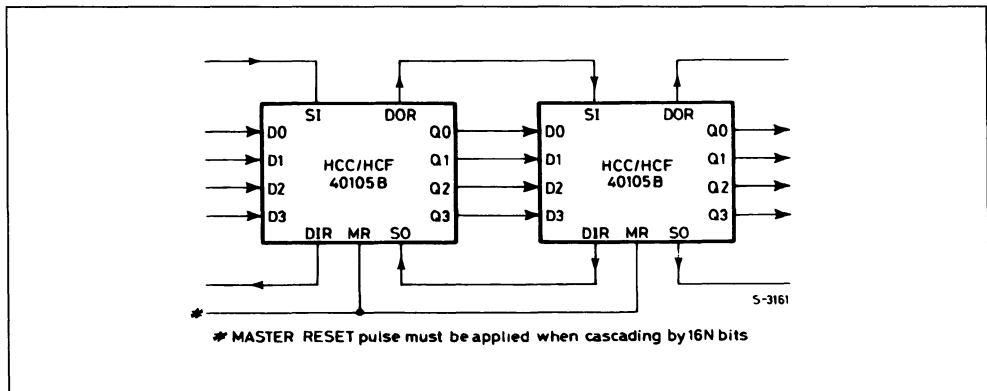


Dynamic Power Dissipation.

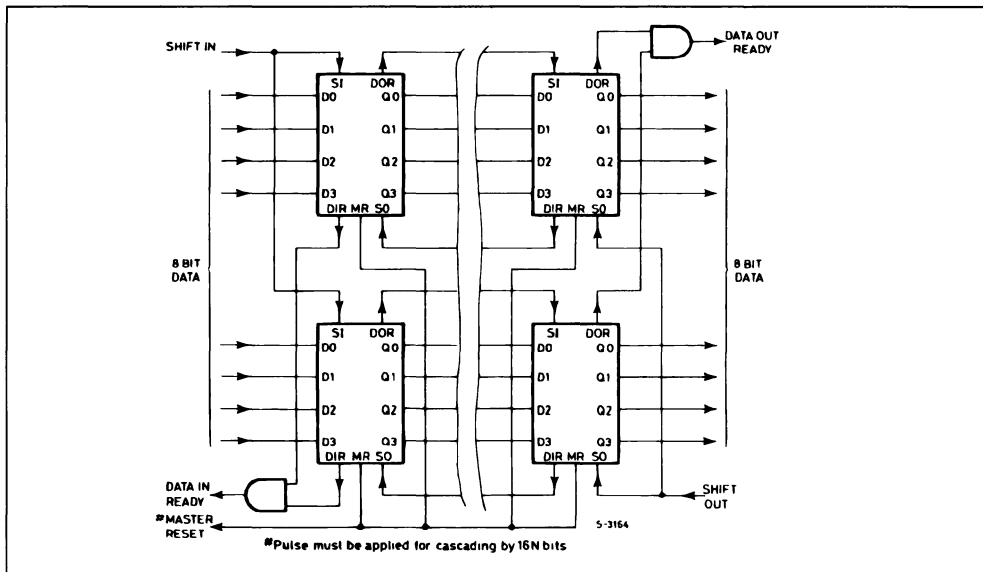


TYPICAL APPLICATIONS

EXPANSION, 4 BITS-WIDE-BY-16 N-BITS LONG.



EXPANSION, 8 BITS-WIDE-BY-16 N-BITS LONG.



APPLICATIONS INFORMATION

LOADING DATA

Data can be entered whenever the DATA-IN READY (DIR) flag is high, by a low to high transition on the SHIFT-IN (SI) input. This input must go low momentarily before the next word is accepted by the FIFO. The DIR flag will go low momentarily, until the data have been transferred to the second location. The flag will remain low when all 16-word locations are filled with valid data, and further pulses on the SI input will be ignored until DIR goes high.

UNLOADING DATA

As soon as the first word has rippled to the output, DATA-OUT READY (DOR) goes high, and data can be removed by a falling edge on the SO input. This falling edge causes the DOR signal to go low while the word on the output is dumped and the next word moves to the output. As long as valid data are available in the FIFO, the DOR signal will go high again signifying that the next word is ready at the output. When the FIFO is empty, DOR will remain low, and any further commands will be ignored until a "1" marker ripples down to the last control register, when DOR goes high. Unloading of data is inhibited while the 3-state control input is high. The 3-state control signal should not be shifted from high to low (data outputs turned on)

while the SHIFT-OUT is at logic 0. This level change would cause the first word to be shifted out (unloaded) immediately and the data to be lost.

CASCADING

The HCC/HCF40105B can be cascaded to form longer registers simply by connecting the DIR to SO and DOR to SI. In the cascaded mode, a MASTER RESET pulse must be applied after the supply voltage is turned on. For words wider than 4 bits, the DIR and the DOR outputs must be gated together with AND gates. Their outputs drive the SI and SO inputs in parallel, if expanding is done in both directions.

3-STATE OUTPUTS

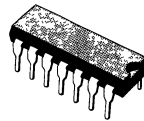
In order to facilitate data busing, 3-state outputs are provided on the data output lines, while the load condition of the register can be detected by the state of the DOR output.

MASTER RESET

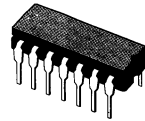
A high on the MASTER RESET (MR) sets all the control logic marker bits to "0". DOR goes low and DIR goes high. The contents of the data register are not changed, only declared invalid, and will be superseded when the first word is loaded.

HEX SCHMITT TRIGGERS

- SCHMITT-TRIGGER ACTION WITH NO EXTERNAL COMPONENTS
- HYSTERESIS VOLTAGE (TYP.) 0.9V AT $V_{DD} = 5V$, 2.3V AT $V_{DD} = 10V$ AND 3.5V AT $V_{DD} = 15V$
- NOISE IMMUNITY GREATER THAN 50%
- NO LIMIT ON INPUT RISE AND FALL TIME
- LOW V_{DD} TO V_{SS} CURRENT DURING SLOW INPUT RAMP
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)



C1
(Plastic Chip Carrier)

ORDER CODES :

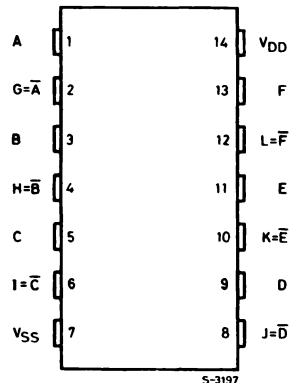
HCC40106BF	HCF40106BM1
HCF40106BEY	HCF40106BC1

DESCRIPTION

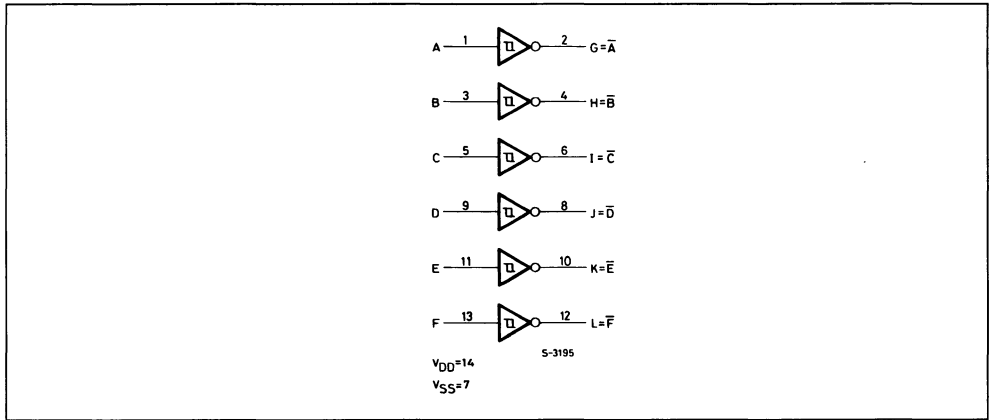
The **HCC40106B** (extended temperature range) and **HCF40106B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF40106B** consists of six Schmitt-trigger circuits. Each circuit functions as an inverter with Schmitt-trigger action on the input. The trigger switches at different points for positive and negative-going signals. The difference between the positive-going voltage (V_P) and the negative-going voltage (V_N) is defined as hysteresis voltage (V_H).

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_I	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

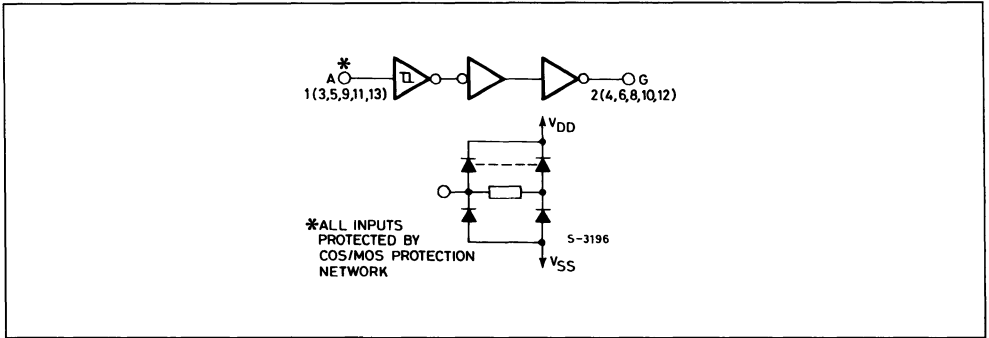
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
		0/20			20		20		0.04	20		600		
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
0/15				15		16		0.02	16		120			
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95				4.95		V	
		0/10	< 1	10	9.95		9.95				9.95			
		0/15	< 1	15	14.95		14.95				14.95			
V _{OL}	Output Low Voltage	5/10	< 1	5		0.05				0.05		0.05	V	
		10/0	< 1	10		0.05				0.05		0.05		
		15/0	< 1	15		0.05				0.05		0.05		
V _P	Positive Trigger Threshold Voltage				5	2.2	3.6	2.2	2.9	3.6	2.2	3.6	V	
					10	4.6	7.1	4.6	5.9	7.1	4.6	7.1		
					15	6.8	10.8	6.8	8.8	10.8	6.8	10.8		
V _N	Negative Trigger Threshold Voltage				5	0.9	2.8	0.9	1.9	2.8	0.9	2.8	V	
					10	2.5	5.2	2.5	3.9	5.2	2.5	5.2		
					15	4	7.4	4	5.8	7.4	4	7.4		
V _H	Hysteresis Voltage				5	0.3	1.6	0.3	0.9	1.6	0.3	1.6	V	
					10	1.2	3.4	1.2	2.3	3.4	1.2	3.4		
					15	1.6	5	1.6	3.5	5	1.6			

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device

* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit			
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *				
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA			
			0/5	4.6		5	-0.64		-0.51	-1		-0.36				
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9				
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4				
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1				
			0/5	4.6		5	-0.52		-0.44	-1		-0.36				
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9				
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4				
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA			
			0/10	0.5		10	1.6		1.3	2.6		0.9				
			0/15	1.6		15	4.2		3.4	6.8		2.4				
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36				
			0/10	0.5		10	1.3		1.1	2.6		0.9				
			0/15	1.5		15	3.6		3.0	6.8		2.9				
		I _{IH} , I _{IL} **	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$		± 0.1		± 1
				HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$		± 0.3		± 1
C _I	Input Capacitance			Any Input					5	7.5		p				

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.

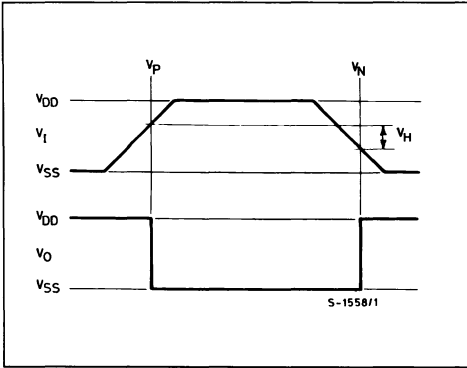
* T_{High} = +125°C for HCC device ; +85°C for HCF device.

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

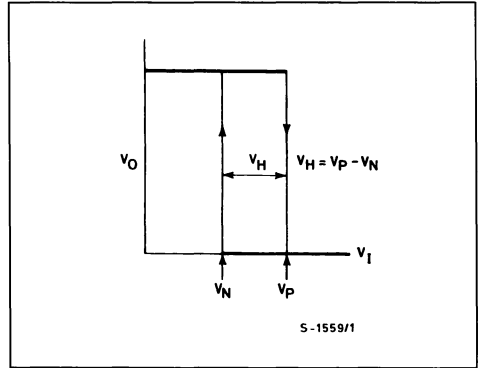
Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PLH} , t _{PHL}	Propagation Delay Time		5		140	280	ns
			10		70	140	
			15		60	120	
t _{THL} , t _{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

HYSTERESIS DEFINITION, CHARACTERISTICS AND TEST SETUP

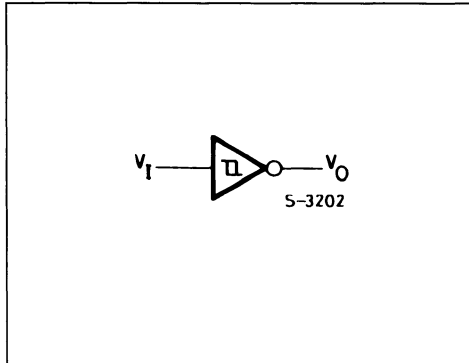
(a) Definition of V_P , V_N and V_H .



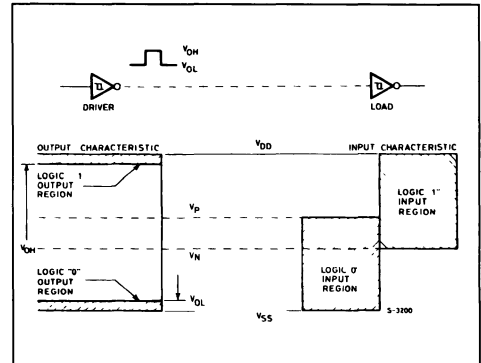
(b) Transfer Characteristic of 1 of 6 gates.



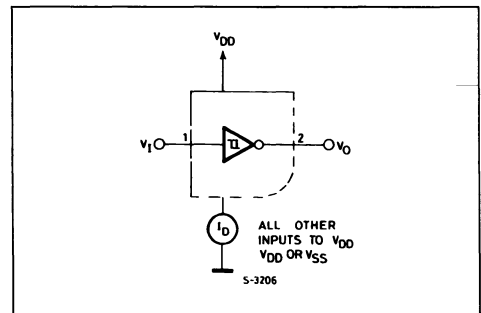
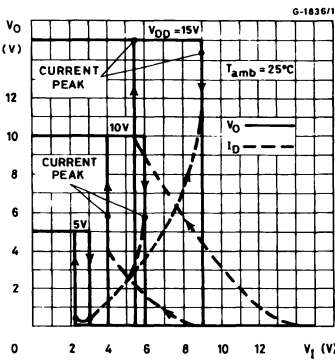
(c) Test Setup.



Input and Output Characteristics.

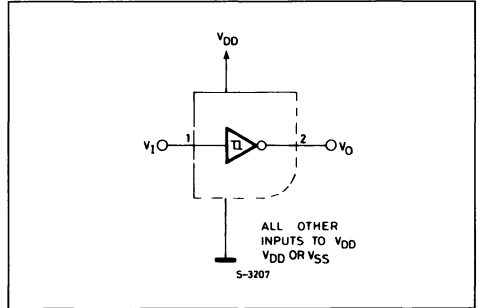
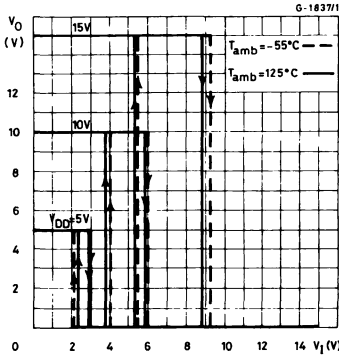


Typical Current Voltage Transfer Characteristics, and Test Circuit.

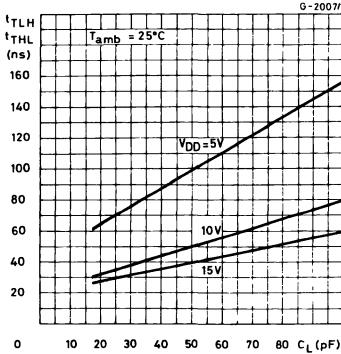


HYSTERESIS DEFINITION, CHARACTERISTICS AND TEST SETUP

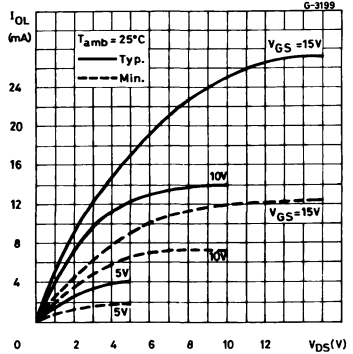
Typical Voltage Transfer Characteristics vs. Temperature, and Test Circuit.



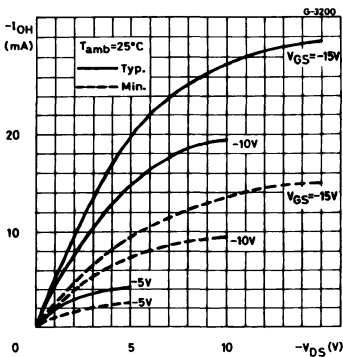
Typical Transition Time vs. Load Capacitance.



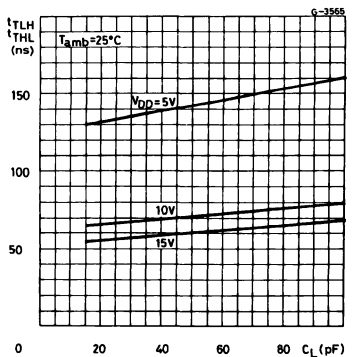
Output Low (sink) Current Characteristics.



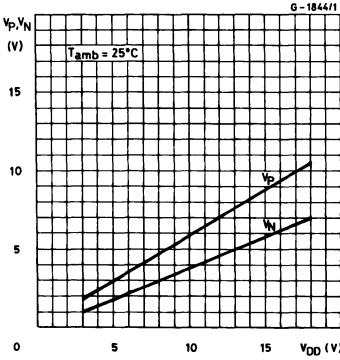
Output High (source) Current Characteristics.



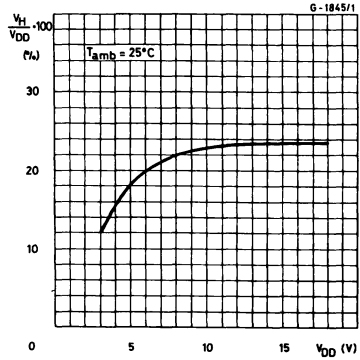
Typical Propagation Delay Time vs. Load Capacitance.



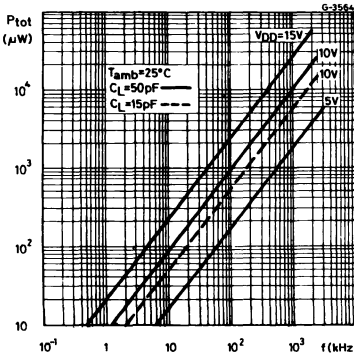
Typical Trigger Threshold Voltage vs. Supply Voltage .



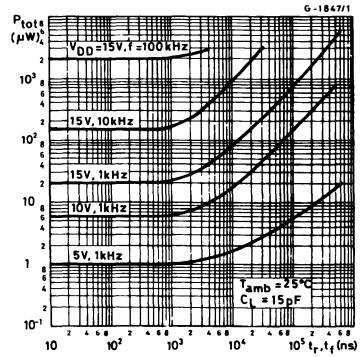
Typical per Cent Hysteresis vs. Supply Voltage.



Typical Power Dissipation per Trigger vs. Input Frequency.

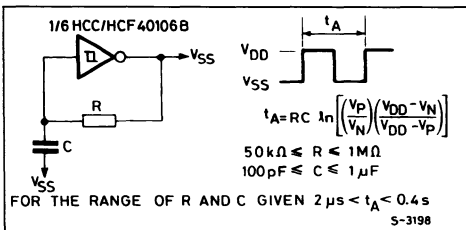


Typical Power Dissipation per Trigger vs. Input Frequency.

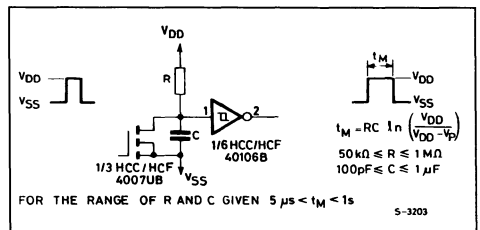


TYPICAL APPLICATIONS

ASTABLE MULTIVIBRATOR.

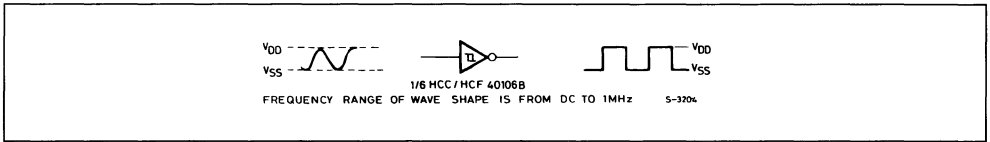


MONOSTABLE MULTIVIBRATOR.



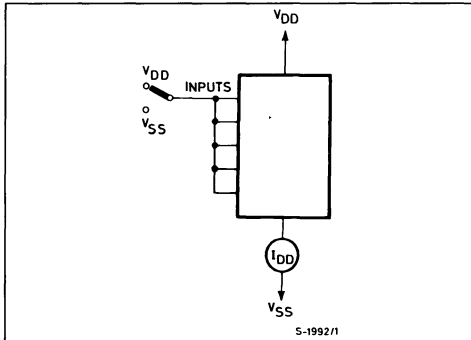
TYPICAL APPLICATIONS (continued)

WAVE SHAPER.

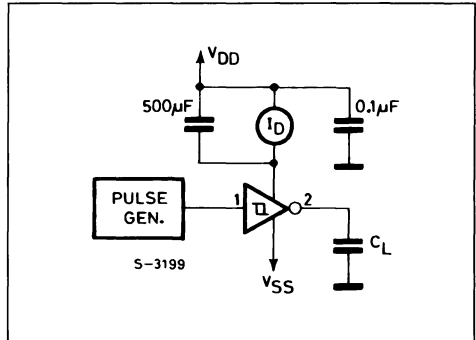


TEST CIRCUITS

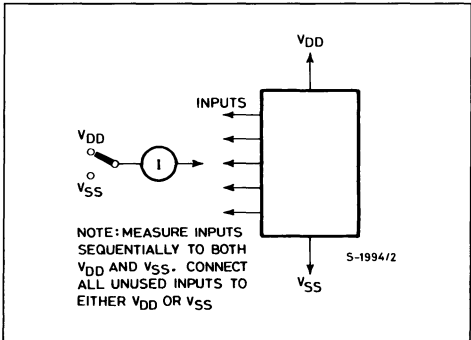
Quiescent Device Current.



Dynamic Power Dissipation.



Input Current .





DUAL 2-INPUT NAND BUFFER/DRIVER

- 32 TIMES STANDARD B-SERIES OUTPUT CURRENT DRIVE SINKING CAPABILITY
– 136mA TYP. @ $V_{DD} = 10V, V_{DS} = 1V$
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

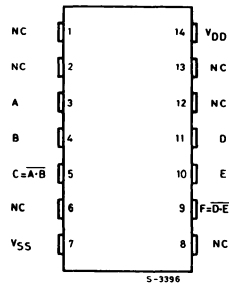
EY (Plastic Package) **F** (Ceramic Frit Seal Package)

M1 (Micro Package) **C1** (Plastic Chip Carrier)

ORDER CODES

HCC40107BF	HCF40107BM1
HCF40107BEY	HCF40107BC1

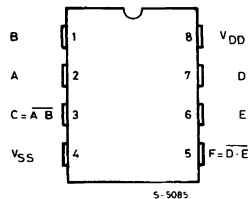
PIN CONNECTIONS



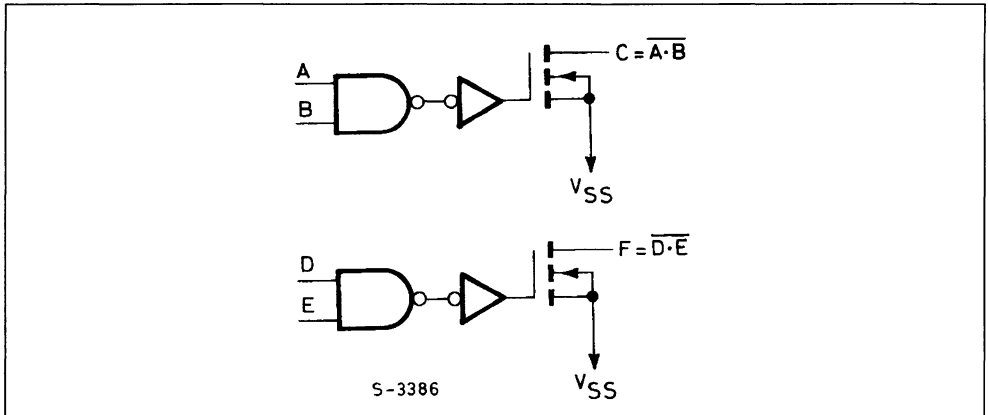
DESCRIPTION

The **HCC40107B** (extended temperature range) and **HCF40107B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line ceramic package 8-lead minidip plastic package and 8-lead plastic micropackage.

The **HCC/HCF40107B** is a dual 2-input NAND buffer/driver containing two independent 2-input NAND buffers with open-drain single n-channel transistor outputs. This device features a wired-OR capability and high output sink current capability (136mA typ. at $V_{DD} = 10V, V_{DS} = 1V$).



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC types HCF types	- 0.5 to + 20 - 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = full package-temperature Range	100	
T _{op}	Operating Temperature : HCC types HCF types	- 55 to + 125 - 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

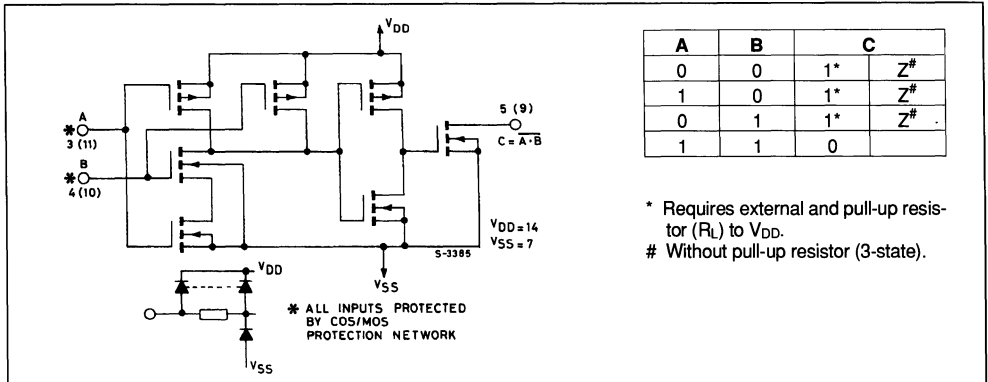
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltages values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

SCHEMATIC DIAGRAM AND TRUTH TABLE



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V_I (V)	V_O (V)	$ I_{O1} $ (μA)	V_{DD} (V)	T_{Low}^*		25°C			T_{High}^*			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I_L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μA
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
		0/15			15		16		0.02	16		120		
V_{IH}^{**}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V_{IL}^{**}	Input Low Voltage		4.5	< 1	5		1.5			1.5		1.5	V	
			9	< 1	10		3			3		3		
			13.5	< 1	15		4			4		4		

* T_{Low} = - 55°C for HCC device ; - 40°C for HCF device.
 * T_{High} = + 125°C for HCC device ; + 85°C for HCF device.
 * The Noise Margin, full package temperature range, R_L to V_{DD} = $10k\Omega \cdot 1V$ min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V.
 ** Measured with external pull-up resistor, R_L = $10k\Omega$ to V_{DD} .
 *** Forced output disabled.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OL}	Output Sink Current	HCC Types	5	0.4		5	21		16	32		12		mA
			5	1		5	44		30	68		25		
			10	0.5		10	49		37	74		28		
			10	1		10	89		68	136		51		
			15	0.5		15	66		50	100		38		
		HCF Types	5	0.4		5	17		13.6	32		12		
			5	1		5	35.7		25.5	68		22		
			10	0.5		10	39.1		31.4	74		27		
			10	1		10	72.2		57.8	136		51		
			15	0.5		15	53.5		42.5	100		37		
I _{OH}	Output Drive Current	No Internal Pull-up Device										mA		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15	Any Input		15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
I _{OH} , I _{OL} ***	3-State Output Leakage Current	HCC Types	0/18	18		18		2		$\pm 10^{-4}$	2		20	μ A
		HCF Types	0/15	15		15		2		$\pm 10^{-4}$	2		20	
C _I	Input Capacitance	Any Input						5	7.5				pF	
C _O	Output Capacitance	Any Output						30					pF	

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device* The Noise Margin, full package temperature range, R_L to V_{DD} = 10k Ω 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V** Measured with external pull-up resistor, R_L = 10k Ω to V_{DD}

*** Forced output disabled

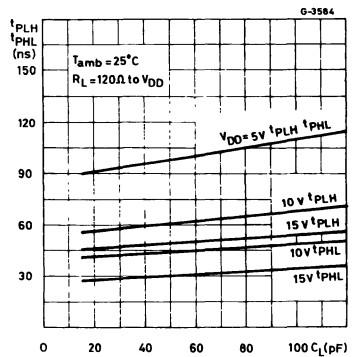
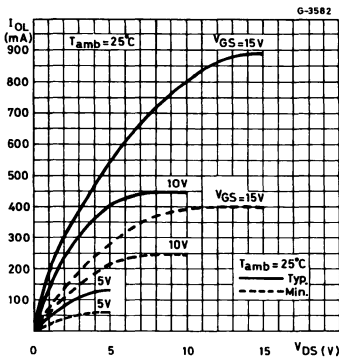
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time High to Low	$R_L^* = 120\Omega$	5		100	200	ns
			10		45	90	
			15		30	60	
	Low to High	$R_L^* = 120\Omega$	5		100	200	ns
			10		60	120	
			15		50	100	
t_{THL} , t_{TLH}	Transition Time High to Low	$R_L^* = 120\Omega$	5		50	100	ns
			10		20	40	
			15		10	20	
	Low to High	$R_L^* = 120\Omega$	5		50	100	ns
			10		35	70	
			15		25	50	

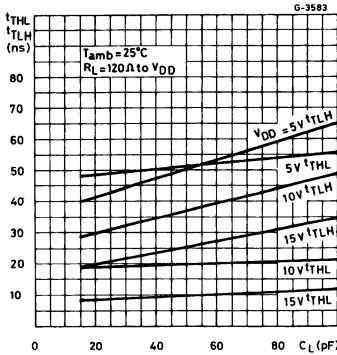
* R_L is external pull-up resistor to V_{DD} .

Output Low (sink) Current Characteristics.

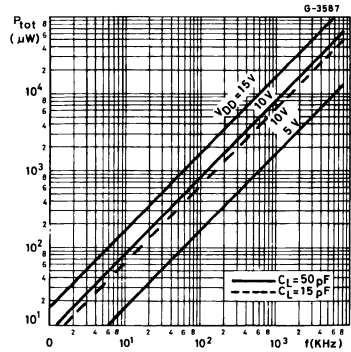
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.



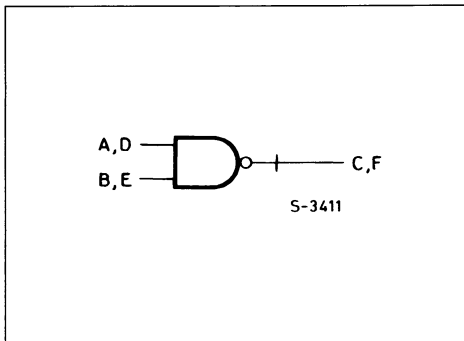
Typical Dynamic Power Dissipation vs. Input Frequency.



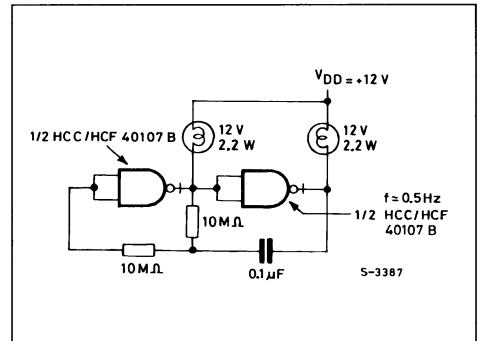
TYPICAL APPLICATIONS

The bar on the output line of this logic diagram indicates that the output is open drain as is shown in the previous schematic diagram and truth table.

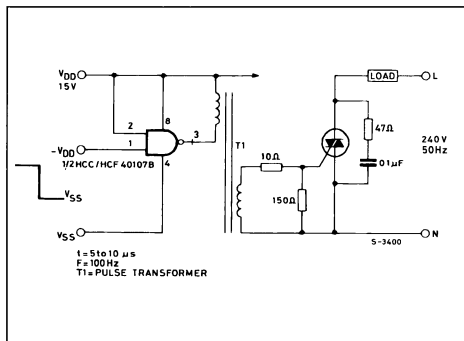
Logic Diagram of The HCC/HCF40107B nand Buffer.



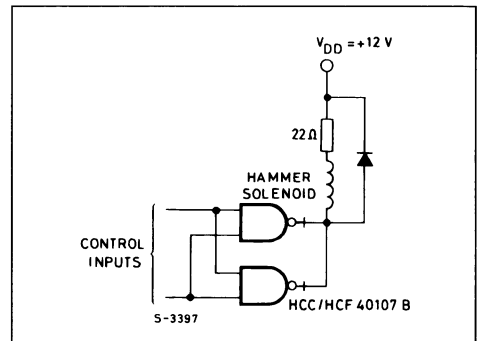
A 2.2-watt Incandescent Lamp-driver Circuit.



Interface of 40107B with Triac, with COS/MOS Component and Triac isolated.

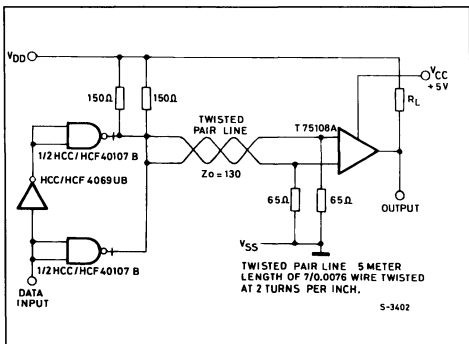


Solenoid Driver Circuit.

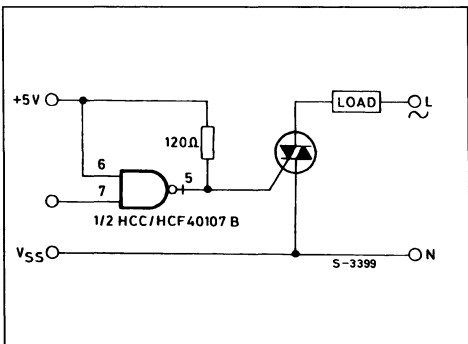


TYPICAL APPLICATIONS (continued)

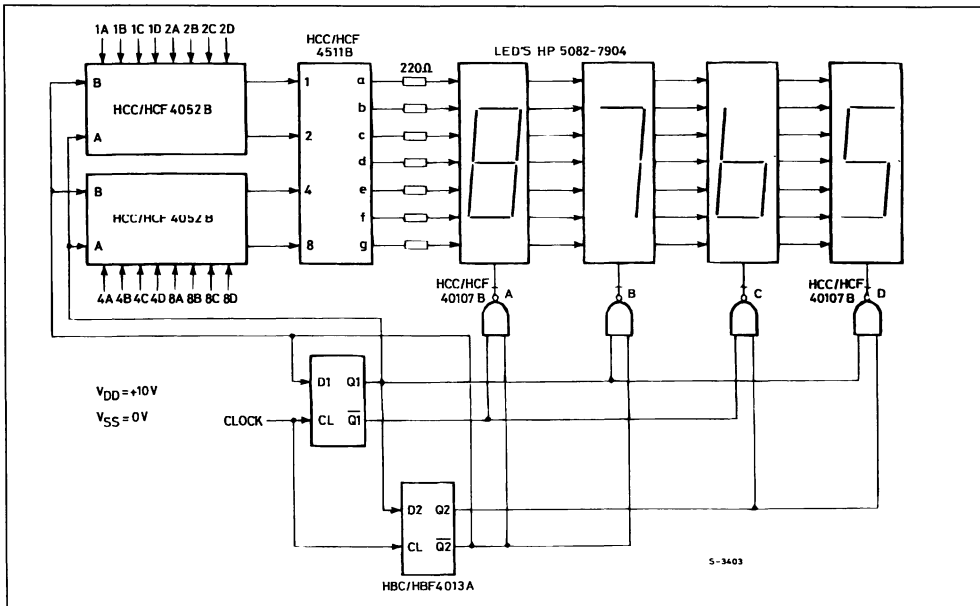
Line-driver Circuit.



Direct Dc Driver Interface of 40107B with a Triac.

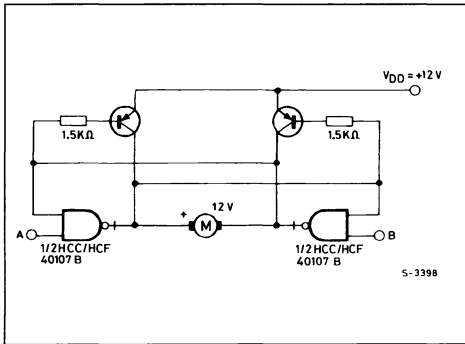


Multiplexed Led Circuit.



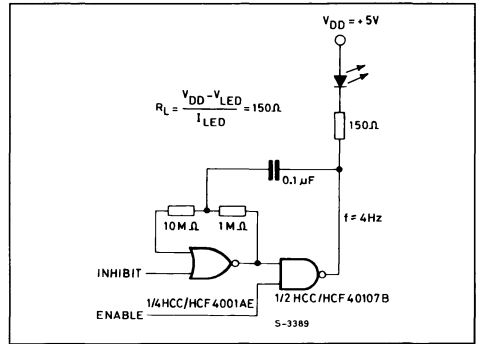
TYPICAL APPLICATIONS (continued)

Motor-controller Circuit.



A	B	Motor Function
0	0	OFF
1	0	COUNTER CLOCKWISE
1	1	AS PREVIOUS STATE
0	1	CLOCKWISE
1	1	AS PREVIOUS STATE

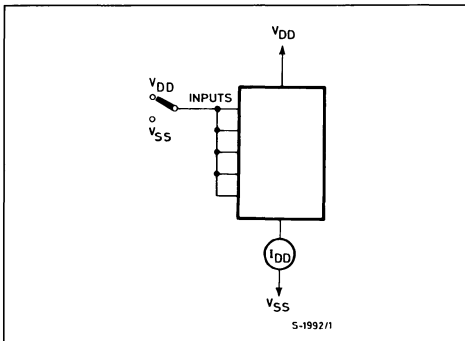
Led Driver Circuit.



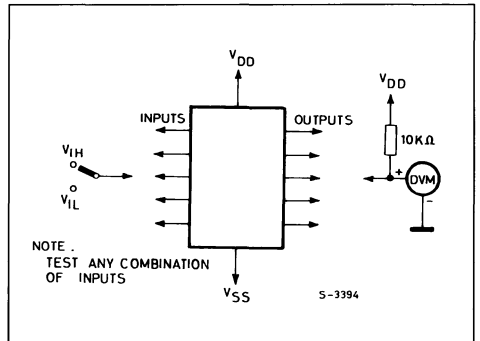
INHIBIT	ENABLE	OUTPUT
0	0	OFF
1	0	OFF
0	1	OFF
0	1	ON

TEST CIRCUITS

Quiescent Device Current.



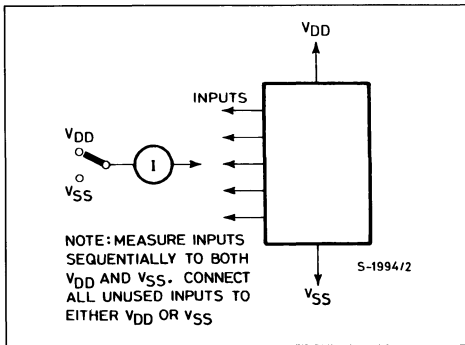
Input Voltage.



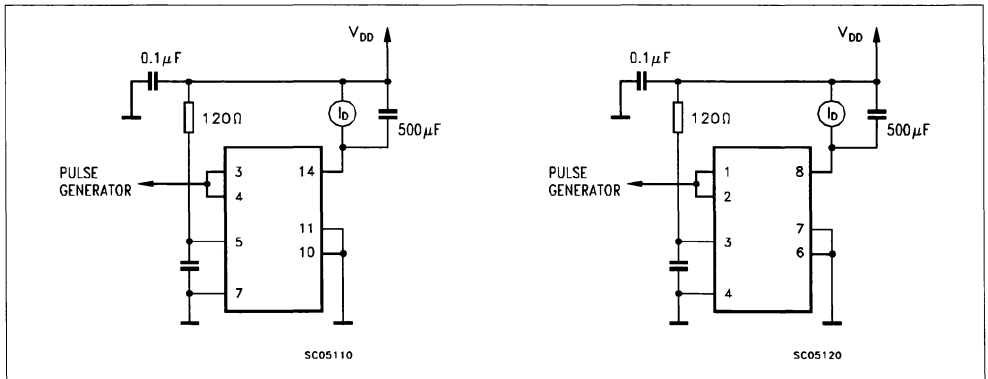
NOTE .
TEST ANY COMBINATION
OF INPUTS

TEST CIRCUITS (continued)

Dynamic Power Dissipation.



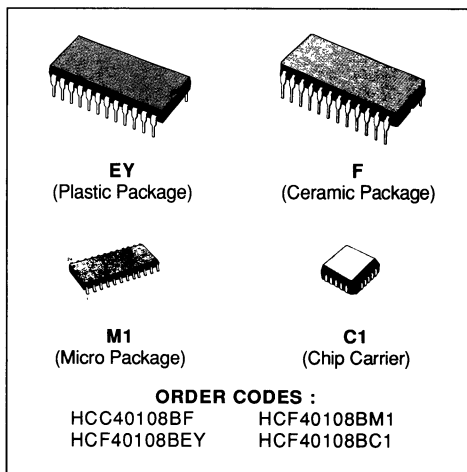
Dynamic Power Dissipation.



4 x 4 MULTIPORT REGISTER

- FOUR 4-BIT REGISTERS
- ONE INPUT AND TWO OUTPUT BUSES
- UNLIMITED EXPANSION IN BIT AND WORD DIRECTION
- DATA LINES HAVE LATCHED INPUTS
- 3-STATE OUTPUTS
- SEPARATE CONTROL OF EACH BUS, ALLOWING SIMULTANEOUS INDEPENDENT READING AND ANY OF FOUR REGISTERS ON BUS A AND BUS B AND INDEPENDENT WRITING INTO ANY ANY OF THE FOUR REGISTERS
- 40108B IS PIN COMPATIBLE WITH INDUSTRY TYPE MC14580
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18V AND 250c FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No 13a, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

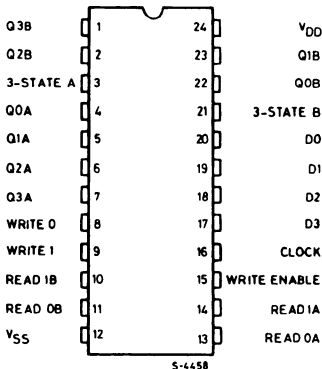
no new data is netered. In either case, the contents of any word may be accessed via the read address lines independent of the state of the CLOCK input.



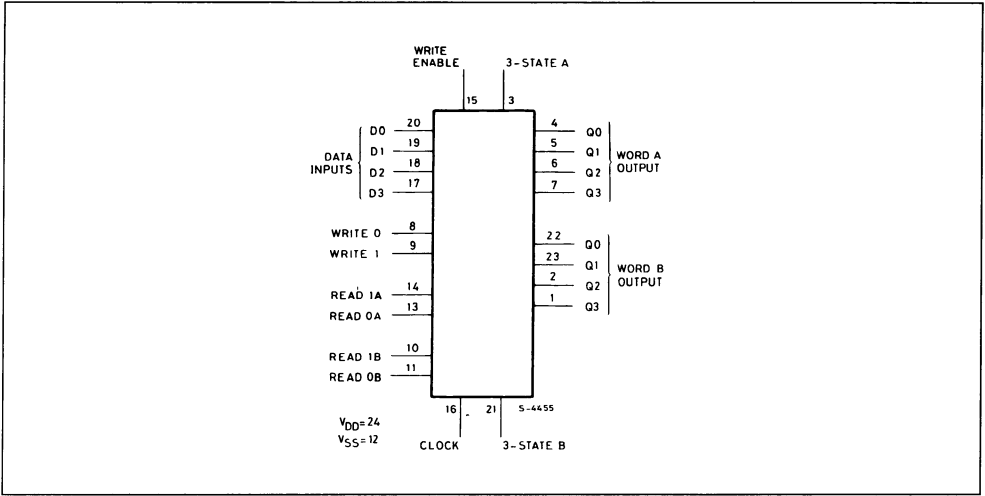
DESCRIPTION

The HCC40108B (extended temperature range) and HCF40108B (intermediate temperature range) are monolithic integrated circuits, available in 24 lead dual in line plastic or ceramic package and plastic micropackage. The HCC/HCF40108B is a 4 X 4 multiport register containing four 4-bit register, write address decoder, two separate read address decoders, and two 3-state output buses. When the ENABLE input is low, the corresponding output bus is switched, independently of the clock, to a high impedance state. The high impedance third state provides the outputs with the capability of being connected to the bus lines in a bus organized system without the need for interface or pull-up components. When the WRITE ENABLE input is high, all data input lines are latched on the positive transition of the CLOCK and the data is entered into the word selected by the write address lines. When WRITE ENABLE is low, the CLOCK is inhibited and

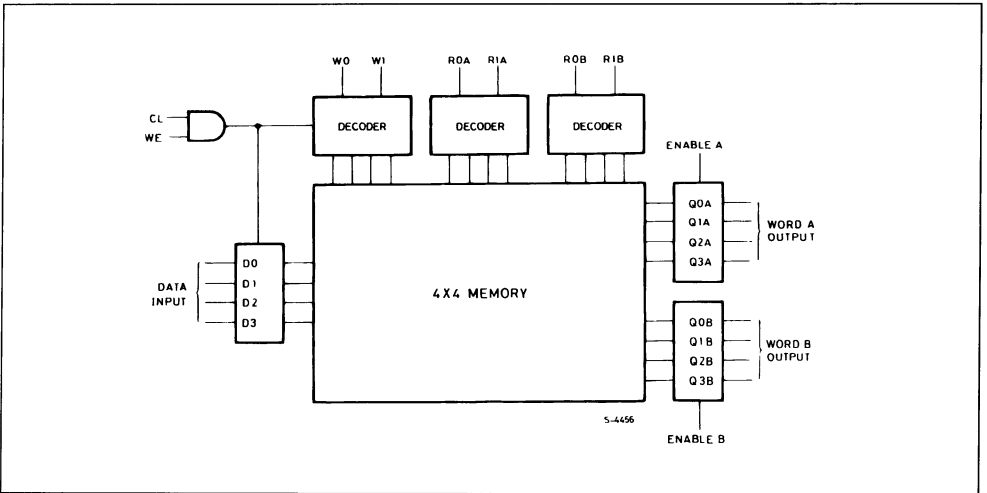
PIN CONNECTIONS



FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20	V
		-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C






Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C

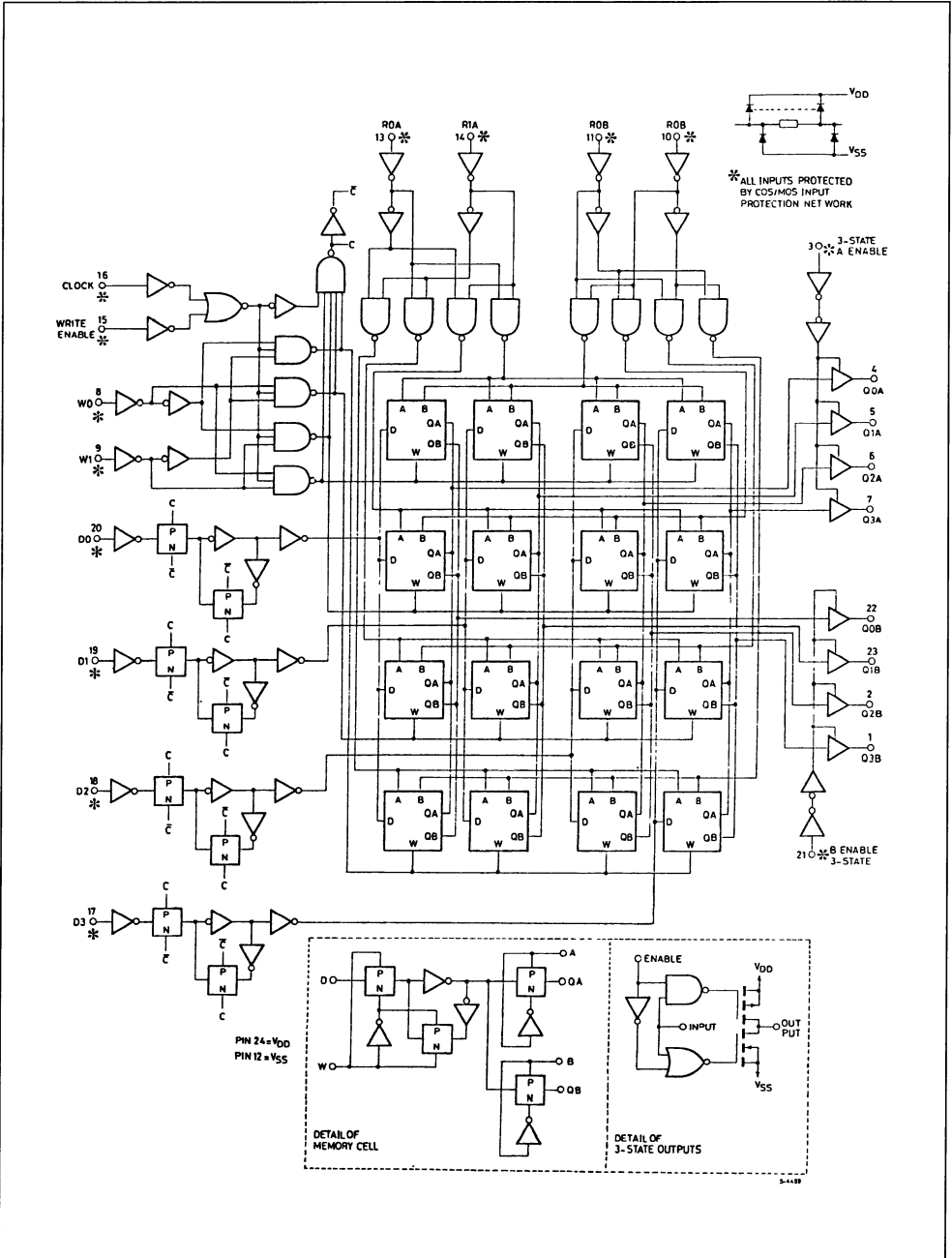
TRUTH TABLE

CLOCK	Write Enable	Write 1	Write 2	Read 1A	Read 0A	Read 1B	Read 0B	En-able A	En-able B	D _n	Q _{nA}	Q _{nB}
	1	S1	S2	S1	S2	S1	S2	1	1	1	1	1
	1	S1	S2	S1	S2	S1	S2	1	0	0	0	0
X	X	X	X	X	X	X	X	0	X	Z	Z	Z
	1	0	0	0	1	1	0	1	1	D _n to word 0	Word 1 Out	Word 2 Out
	0	0	0	0	1	1	0	1	1	Word 0 not altered	Word 1 Out	Word 2 Out
X	X	X	X	1	0	0	1	1	X	X	Word 2 Out	Word 1 Out
	X	X	X	X	X	X	X	1	1	X	NC	NC

1 = HIGH LEVEL, 0 = LOW LEVEL, X = DON'T CARE, Z = HIGH IMPEDANCE

S1 and S2 refer to input strates of either 1 or 0

SCHEMATIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _o (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
		0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A
		HCF Types	0/15	Any Input		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1	
I _{OH} , I _{OL} **	3-State Output Leakage Current	HCC Types	0/18	0/18		18		\pm 0.4		\pm 10 ⁻⁴	\pm 0.4		\pm 12	μ A
		HCF Types	0/15	0/15		15		\pm 1.0		\pm 10 ⁻⁴	\pm 1.0		\pm 7.5	
C _I	Input Capacitance	Any Input							5	7.5			pF	

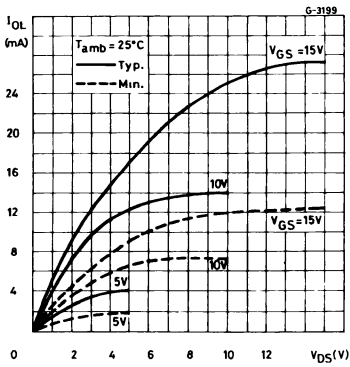
* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF deviceThe Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

** Forced output disable

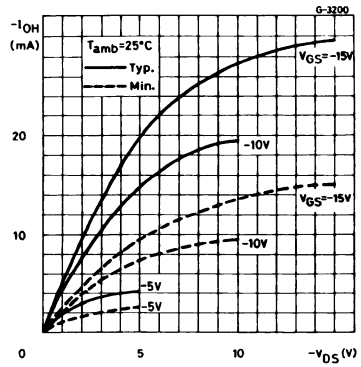
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time Clock or Write Enable to Q		5		360	720	ns
			10		140	280	
			15		100	200	
	Propagation Delay Time Read or Write Address to Q		5		300	600	
			10		120	240	
			15		85	170	
t_{PZH} t_{PHZ}	3-State Disable Delay Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{PZL} t_{PLZ}	3-State Display Delay Time		5		130	260	ns
			10		60	120	
			15		50	100	
t_{TLH} t_{THL}	Output Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Setup Time Data to Clock $t_{s(D)}$		5	0	-95		ns
			10	0	-35		
			15	0	-20		
	Setup Time Write Enable to Clock $t_{s(WE)}$		5	250	125		
			10	100	50		
			15	70	35		
	Setup Time Write Address to Clock $t_{s(WA)}$		5	250	125		
			10	100	50		
			15	70	35		
t_r, t_s	Clock Rise and Fall Time		5			15	μs
			10			5	
			15			5	
t_{hold}	Hold Time Data to Clock $t_{s(D)}$		5	220	110		ns
			10	100	50		
			15	80	40		
	Hold Time Write Enable to Clock $t_{s(WE)}$		5	270	135		
			10	130	65		
			15	80	40		
	Hold Time Write Address to Clock $t_{s(WA)}$		5	330	165		
			10	140	70		
			15	90	45		
t_w	Clock Pulse Width Clock or Write Enable $t_{w(CL)}$		5	350	175		ns
			10	130	65		
			15	90	45		
	Clock Pulse Width Write Address $t_{w(WA)}$		5	300	150		
			10	150	75		
			15	90	45		
f_{CL}	Maximum Clock Input Frequency		5	1.5	3	MHz	
			10	3.5	7		
			15	4.5	9		

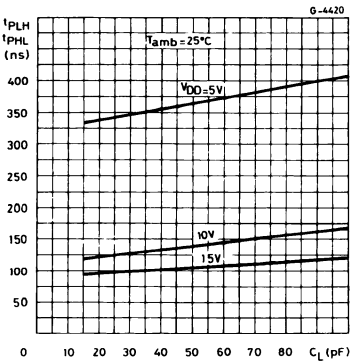
Output Low (sink) Current Characteristics



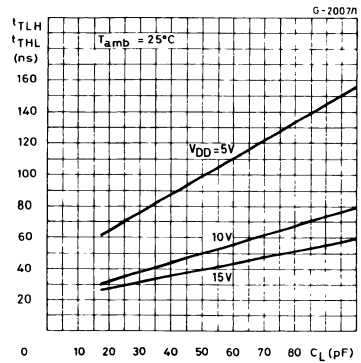
Output High (source) Current Characteristics



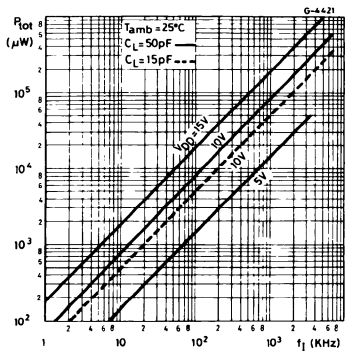
Typical Propagation Delay Time vs Load Capacitance (CL or WE to Q)



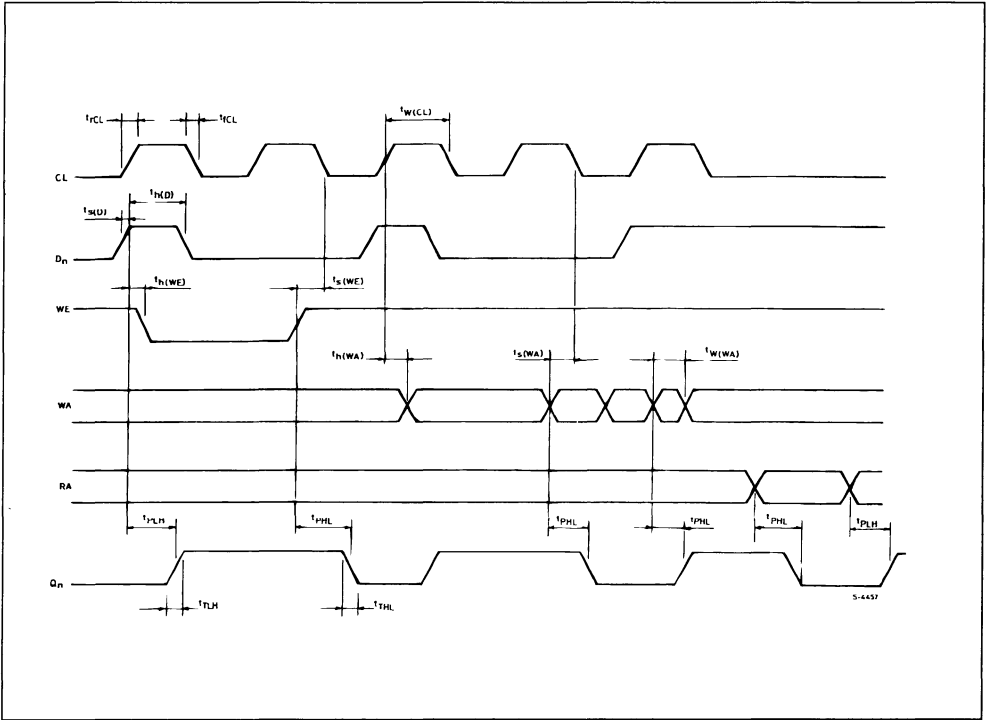
Typical Transition Time vs Load Capacitance



Typical Dynamic Power Dissipation vs Input Frequency

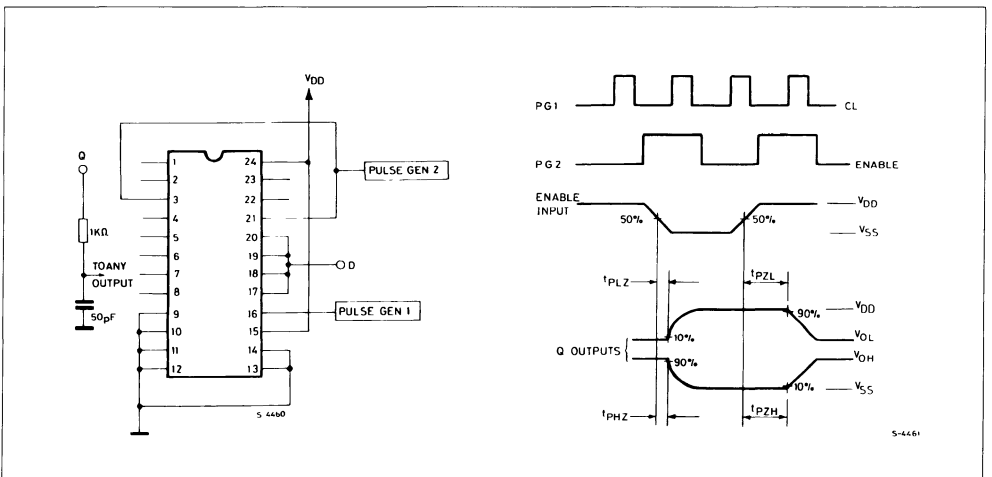


TIMING DIAGRAM

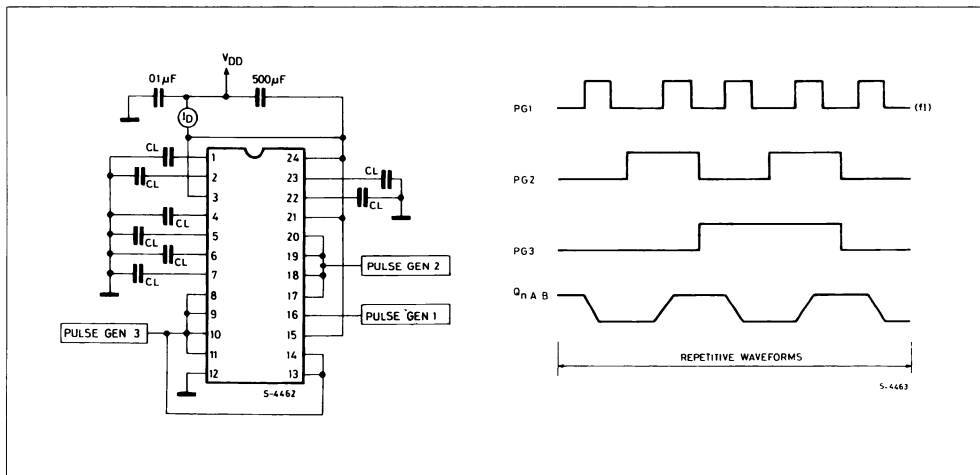


TEST CIRCUITS

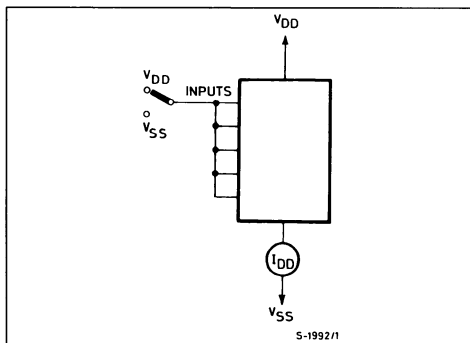
Output Enable Delay Times and Waveforms



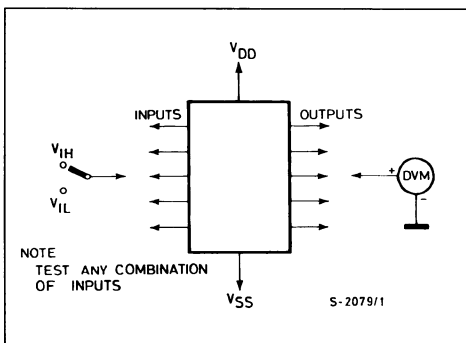
Power Dissipation and Waveforms



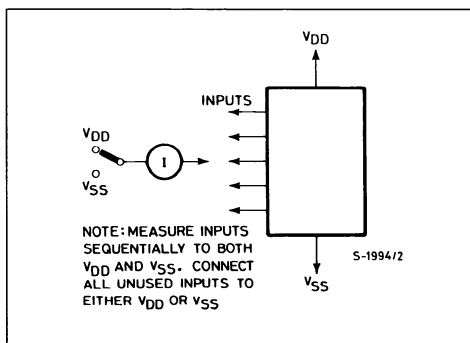
Quiescent Device Current.



Noise Immunity.



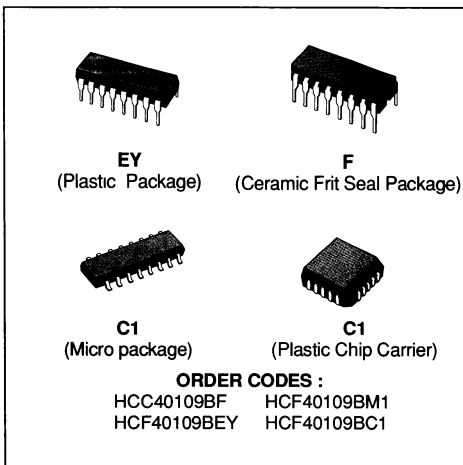
Input Leakage Current.



QUAD LOW-TO-HIGH VOLTAGE LEVEL SHIFTER

- INDEPENDENCE OF POWER SUPPLY SEQUENCE CONSIDERATIONS – V_{CC} CAN EXCEED V_{DD} , INPUT SIGNALS CAN EXCEED BOTH V_{CC} AND V_{DD}
- UP AND DOWN LEVEL-SHIFTING CAPABILITY
- THREE-STATE OUTPUTS WITH SEPARATE ENABLE CONTROLS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

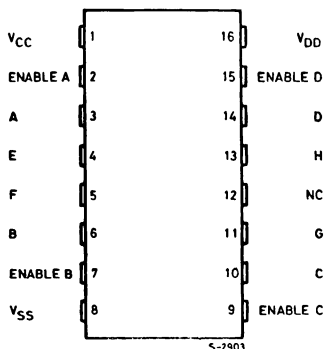
controls produces a high-impedance state in the corresponding output.



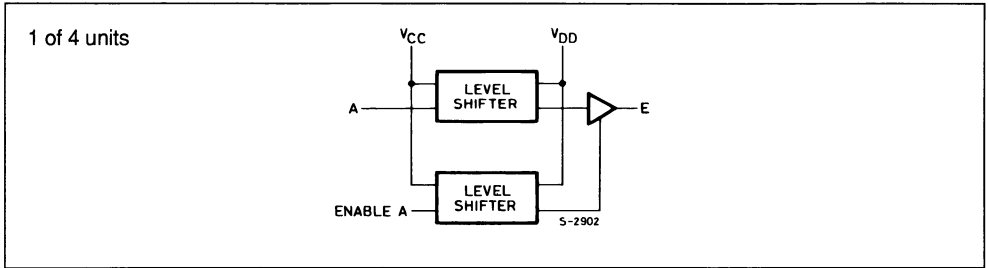
DESCRIPTION

The **HCC40109B** (extended temperature range) and **HCF40109B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF40109B** contains four low-to-high-voltage level-shifting circuits. Each circuit will shift a low-voltage digital-logic input signal (A, B, C, D) with logical 1 = V_{CC} and logical 0 = V_{SS} to a higher-voltage output signal (E, F, G, H) with logical 1 = V_{DD} and logical 0 = V_{SS} . The **HCC/HCF40109B**, unlike other low-to-high level-shifting circuits, does not require the presence of the high-voltage supply (V_{DD}) before the application of either the low-voltage supply (V_{CC}) or the input signals. There are no restrictions on the sequence of application of V_{DD} , V_{CC} , or the input signals. In addition, there are no restrictions on the relative magnitudes of the supply voltages or input signals within the device maximum ratings; V_{CC} may exceed V_{DD} , and input signals may exceed V_{CC} , and V_{DD} . When operated in the mode $V_{CC} = V_{DD}$, the **HCC/HCF40109B**, will operate as a high-to-low level-shifter. The **HCC/HCF 40109B** also features individual three-state output capability. A low level on any of the separately enabled three-state output

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types	- 0.5 to + 20	V
	HCF Types	- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	100	mW
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

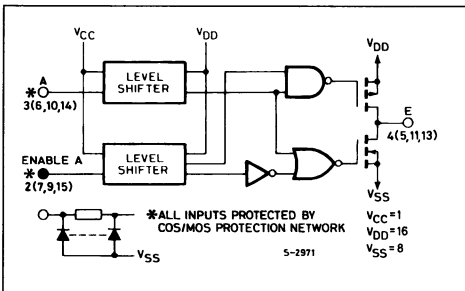
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage are with respect to V_{SS} (GND)

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

Mode	Inputs		Outputs
	A, B, C, D	Enable	E, F, G, H
Low to High Level Shift	0	1	0
	1	1	1
	X	0	Z

LOGIC 0 = LOW (V_{SS})

X = Don't Care.

Z = High Impedance.

LOGIC 1 = V_{CC} at INPUTS and V_{DD} at OUTPUTS.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions					Value						Unit	
			V _I (V)	V _O (V)	I _l (μ A)	V _{CC} (V)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
								Min	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5				5		1		0.02	1		30	μ A
			0/10				10		2		0.02	2		60	
			0/15				15		4		0.02	4		120	
			0/20				20		20		0.04	20		600	
		HCF Types	0/5				5		4		0.02	4		30	
			0/10				10		8		0.02	8		60	
			0/15				15		16		0.02	16		120	
V _{OH}	Output High Voltage	0/5	< 1		5	4.95		4.95			4.95			V	
		0/10	< 1		10	9.95		9.95			9.95				
		0/15	< 1		15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1		5		0.05			0.05		0.05	V		
		10/0	< 1		10		0.05			0.05		0.05			
		15/0	< 1		15		0.05			0.05		0.05			
V _{IH}	Input High Voltage	1/9	< 1	5	10	3.5		3.5			3.5		V		
		1.5/13.5	< 1	10	15	7		7			7				
V _{IL}	Input Low Voltage	1/9	< 1	5	10		1.5			1.5		1.5	V		
		1.5/13.5	< 1	10	15		3			3		3			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5			5	-2	-1.6	-3.2		-1.15	mA		
			0/5	4.6			5	-0.64	-0.51	-1		-0.36			
			0/10	9.5			10	-1.6	-1.3	-2.6		-0.9			
			0/15	13.5			15	-4.2	-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5			5	-1.53	-1.36	-3.2		-1.1			
			0/5	4.6			5	-0.52	-0.44	-1		-0.36			
			0/10	9.5			10	-1.3	-1.1	-2.6		-0.9			
0/15	13.5			15	-3.6	-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4			5	0.64	0.51	1		0.36	mA		
			0/10	0.5			10	1.6	1.3	2.6		0.9			
			0/15	1.5			15	4.2	3.4	6.8		2.4			
		HCF Types	0/5	0.4			5	0.52	0.44	1		0.36			
			0/10	0.5			10	1.3	1.1	2.6		0.9			
			0/15	1.5			15	3.6	3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input			18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15	Any Input			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

** Forced output disabled.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions					Value						Unit	
			V _I (V)	V _O (V)	I _{oI} (V)	V _{CC} (V)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
								Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OH} , I _{OL} **	3-State Output Leakage Current	HCC Types	0/18	0/18				± 0.4		±10 ⁻⁴	± 0.4		± 12	µA	
		HCF Types	0/15	0/15				± 1.0		±10 ⁻⁴	± 1.0		± 7.5		
C _I	Input Capacitance		Any Input								5	7.5		pF	

* T_{Low} = - 55°C for HCC device . - 40°C for HCF device.* T_{High} = + 125°C for HCC device ..+ 85°C for HCF deviceThe Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

** Forced output disabled.

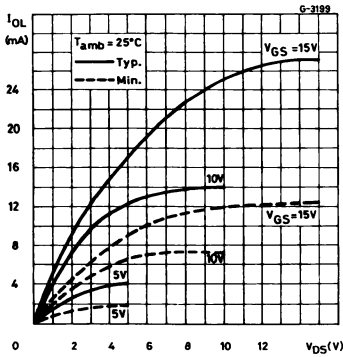
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200kΩ,
typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

Symbol	Parameter	Shifting Mode	Test Conditions		Value			Unit	
			V _{CC} (V)	V _{DD} (V)	Min.	Typ.	Max.		
t _{PHL} , t _{PLH}	Propagation Delay Time (data input to output) High to Low Level	L - H	5	10		300	600	ns	
			5	15		220	440		
			10	15		180	360		
		H - L	10	5		850	1600		
			15	5		850	1600		
			15	10		290	580		
	Low to High Level	L - H	5	10		130	260	ns	
			5	15		120	240		
		H - L	10	5		230	460		
			15	5		230	460		
t _{PHZ}	3-State Disable Delay Time Output High to High Impedance	L - H	5	10		60	120	ns	
			5	15		50	100		
			10	15		35	70		
		H - L	10	5		120	240		
			15	5		120	240		
t _{PZH}	High Impedance to Output High	L - H	5	10		320	640	ns	
			5	15		230	460		
			10	15		180	360		
		H - L	10	5		800	1500		
			15	5		800	1500		
			H - L	15	10		280		560
				15	10		350		700
t _{PLZ}	Output Low to High Impedance	L - H	5	10		370	740	ns	
			5	15		300	600		
			10	15		250	500		
		H - L	10	5		850	1600		
			15	5		850	1600		
			15	10		350	700		

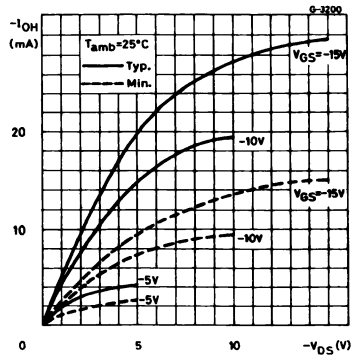
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Shifting Mode	Test Conditions		Value			Unit
			V _{CC} (V)	V _{DD} (V)	Min.	Typ.	Max.	
t _{PZL}	High Impedance to Output Low	L - H	5	10		100	200	ns
			5	15		80	160	
			10	15		40	80	
		H - L	10	5		120	240	
			15	5		120	240	
			15	10		40	80	
t _{THL} , t _{TLH}	Transition Time	L - H	5	10		50	100	ns
			5	15		40	80	
			10	15		40	80	
		H - L	10	5		100	200	
			15	5		100	200	
			15	10		50	100	

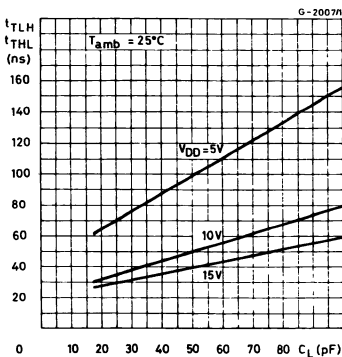
Output Low (sink) Current Characteristics.



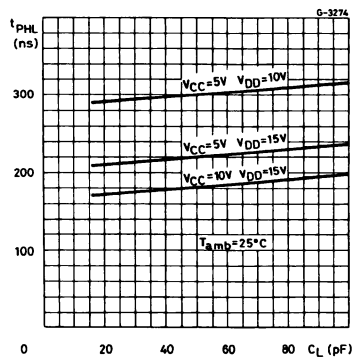
Output High (source) Current Characteristics.



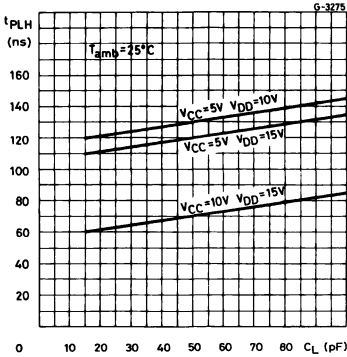
Typical Transition Times vs. Load Capacitance.



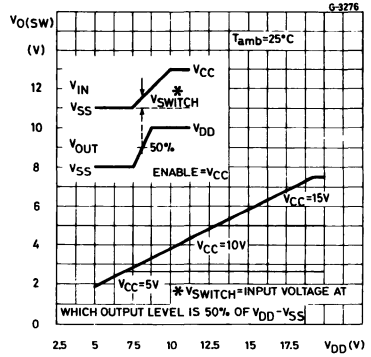
Typical High-to-low Propagation Delay Time vs. Load Capacitance.



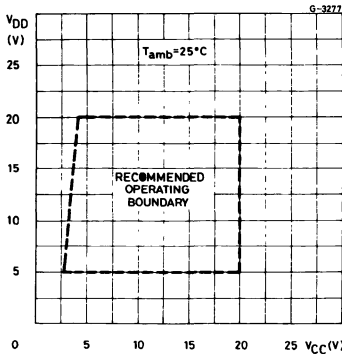
Typical Low-to-high Propagation Delay Time vs. Load Capacitance.



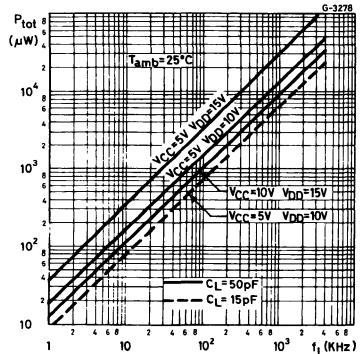
Typical Input Switching vs. High-level Supply Voltage.



High-level Supply Voltage vs. Low-level Supply Voltage.



Typical Dynamic Power Dissipation vs. Input Frequency.



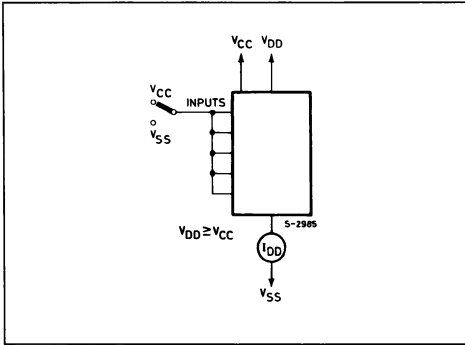
TEST CIRCUITS

Output Enable Delay Times Test Circuit and Waveforms.

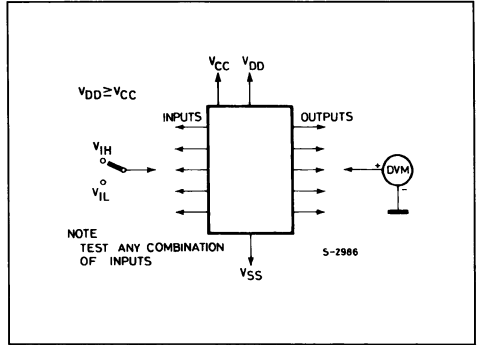
CHAR.	TEST VOLTAGE	
	AT A	AT B
tPHZ	VCC	VSS
tPLZ	VSS	VDD
tPZL	VSS	VDD
tPZH	VCC	VSS

TEST CIRCUITS (continued)

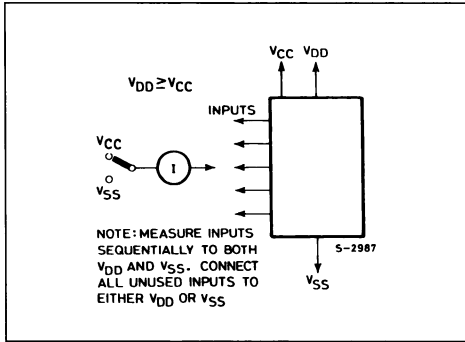
Quiescent Device Current.



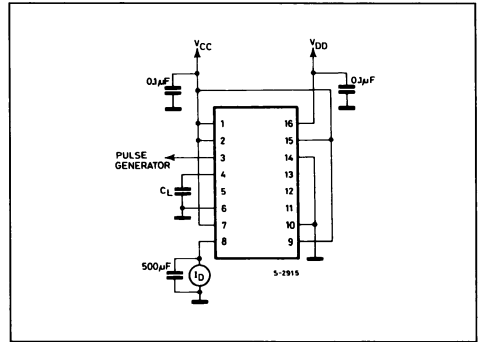
Input Voltage.



Input Leakage Current.



Dynamic Power Dissipation.

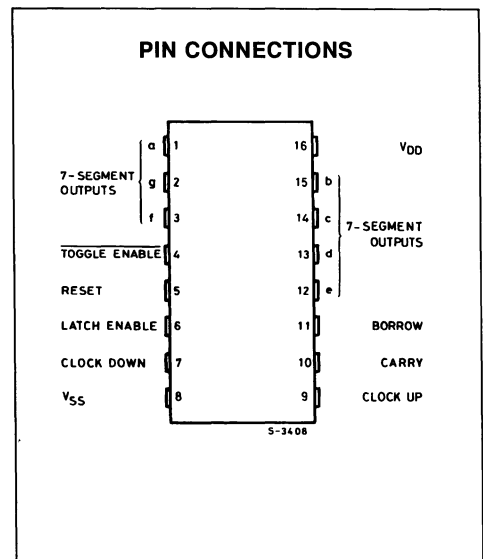
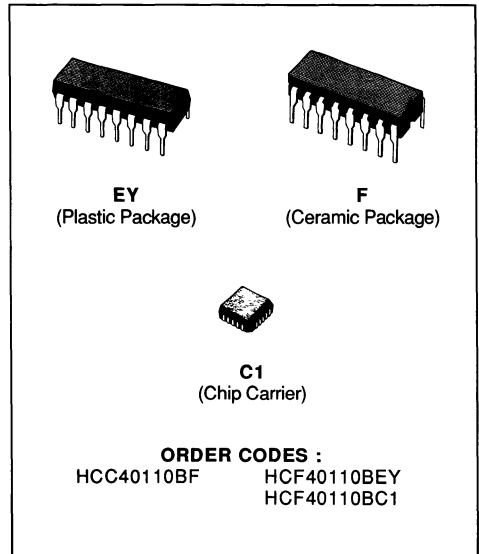


DECADE UP-DOWN COUNTER/DECODER/LATCH/DRIVER

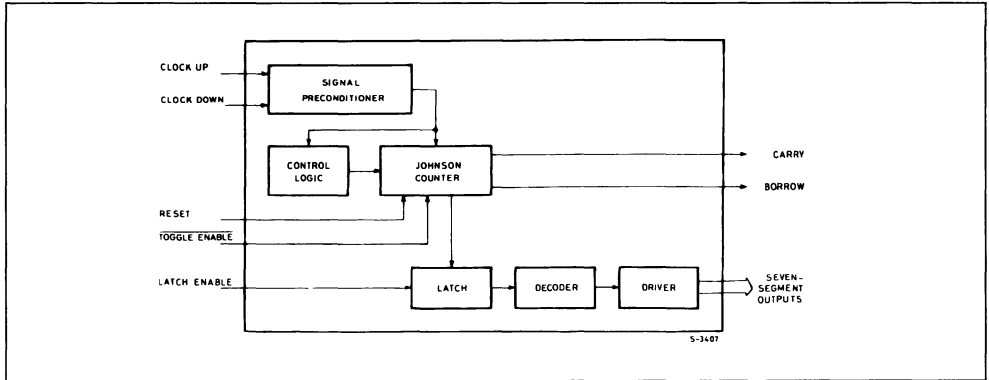
- SEPARATE CLOCK-UP AND CLOCK-DOWN LINES
- CAPABLE OF DRIVING COMMON CATHODE LEDs AND OTHER DISPLAYS DIRECTLY
- ALLOWS CASCADING WITHOUT ANY EXTERNAL CIRCUITRY
- MAXIMUM INPUT CURRENT OF $1 \mu\text{A}$ AT 18 V (full package-temperature range)
- QUIESCENT CURRENT AT 20 V FOR HCC DEVICE
- 5 V, 10 V AND 15 V PARAMETRIC RATINGS
- INPUT CURRENT OF 100 nA AT 18 V AND 25°C FOR HCC DEVICE
- 100 % TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD No. 13 A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC 40110B** (extended temperature range) and **HCF 40110B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The **HCC/HCF 40110B** is a dual-clocked up/down counter with a special preconditioning circuit that allows the counter to be clocked, via positive going inputs, up or down regardless of that state or timing (within 100 ns typ.) of the other clock line. The clock signal is fed into the control logic and Johnson counter after is preconditioned. The outputs of the Johnson counter (which include antilock gating to avoid being locked at an illegal state) are fed into a latch. This data can be fed directly to the decoder through the latch or can be strobed to hold a particular count while the Johnson counter continues to be clocked. The decoder feeds a seven-segment bipolar output driver which can source up to 25 mA to drive LEDs and other displays such as low-voltage fluorescent and incandescent lamps. A short duration negative-going pulse appears on the BORROW output when the count changes from 0 to 9 or the CARRY output when the count changes from 9 to 0. At the other times the BORROW and CARRY output are a logic 1. The CARRY and BORROW outputs can be tied directly to the clock-up and clock-down lines respectively of another HCC/HCF 40110B for easy cascading of several counters.



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

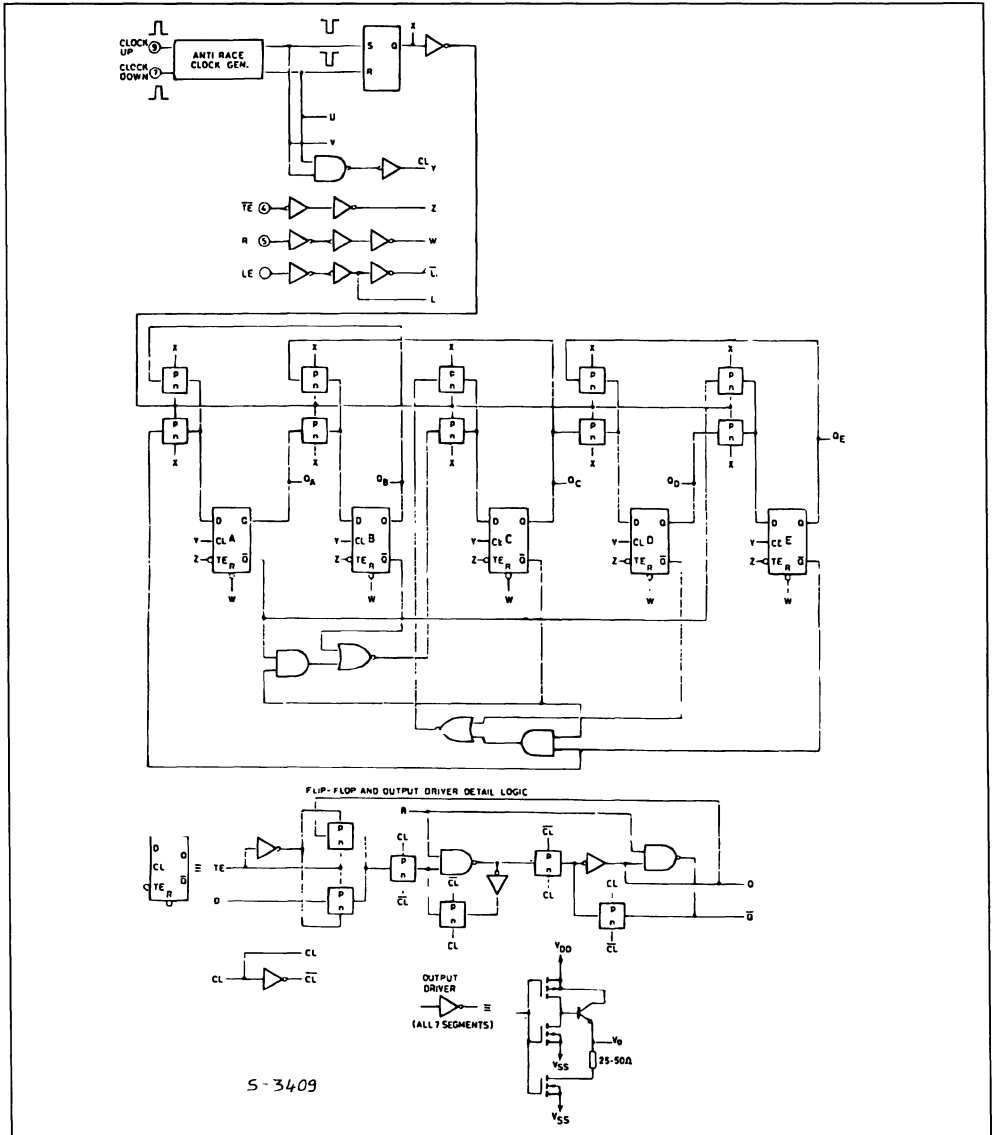
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability

* All voltage values are referred to V_{SS} pin voltage.

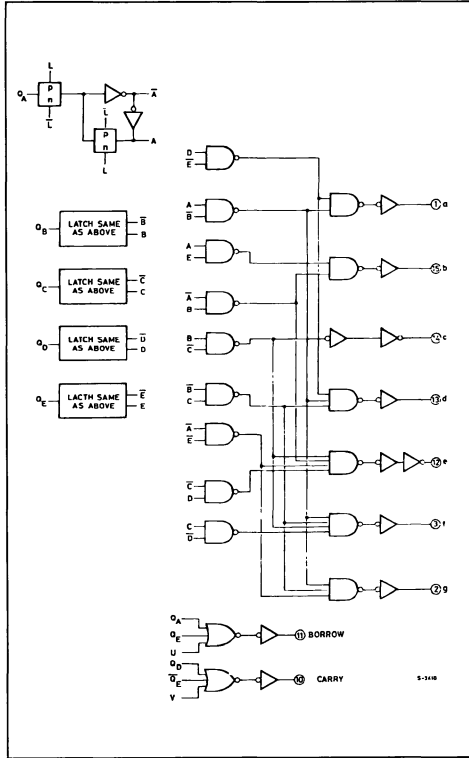
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

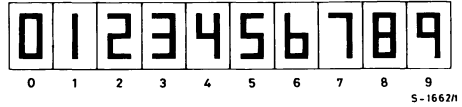
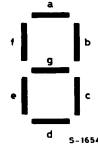
LOGIC DIAGRAMS



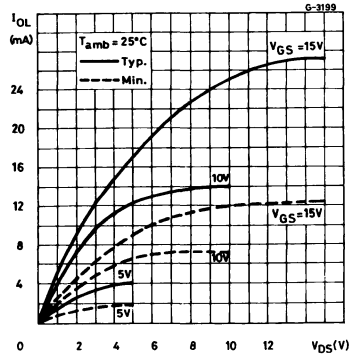
LOGIC DIAGRAM (continued)



DISPLAY SEGMENTS



Output Low (sink) Current Characteristics.



TRUTH TABLE

CLOCK UP*	CLOCK DOWN*	LATCH EN-ABLE	TOGGLE EN-ABLE	RESET	COUNTER	DISPLAY
	X	0	0	0	Increments by 1	Follows Counter
X		0	0	0	Decrement by 1	Follows Counter
		X	X	0	No Change	No Change
X	X	X	X	1	Goes to 00000	Follows Counter (Display = 0)
X	X	X	1	0	Inhibited	Remains Fixed
	X	1	0	0	Increments by 1	Remains Fixed
X		1	0	0	Decrement by 1	Remains Fixed

x = Don't care 1 = High State 2 = Low State

* Typically 100 ns between clock-up and clock-down positive transitions are required to ensure proper counting

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit
			V _I (V)	V _O (V)	I _{oI} (μ A)	V _{DD} (V)	T _{LOW} *		25 °C		T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.	
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150
			0/10			10		10		0.04	10		300
			0/15			15		15		0.04	20		600
			0/20			20		20		0.48	100		3000
		HCF Types	0/5			5		5		0.04	20		150
			0/10			10		10		0.04	40		300
			0/15			15		15		0.04	80		600
V _{OH}	Output High Voltage	0/5			5				4.95				
		0/10			10				9.55				
		0/15			15				14.55				
V _{OL}	Output Low Voltage	5/0			5		0.05		0	0.05		0.05	
		10/0			10		0.05		0	0.05		0.05	
		15/0			15		0.05		0	0.05		0.05	
V _{IH}	Input High Voltage	0.5/3.8			5	3.5		3.5			3.5		
		1/8.8			10	7		7			7		
		1.5/3.8			15	11		11			11		
V _{IL}	Input Low Voltage	0.5/3.8			5		1.5			1.5		1.5	
		1/8.8			10		3			3		3	
		1.5/3.8			15		4			4		4	
V _{OL}	Output Drive Voltage (for HCC/HCF)			0	5				4.55				
				10	5				4.13				
				25	5				3.64				
				0	10				9.55				
				10	10				9.25				
				25	10				8.85				
				0	15				14.55				
				10	15				14.21				
I _{oL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	
		HCF Types	0/15						\pm 0.3				\pm 10 ⁻⁵
C _I	Input Capacitance		Any Input						5	7.5		pF	

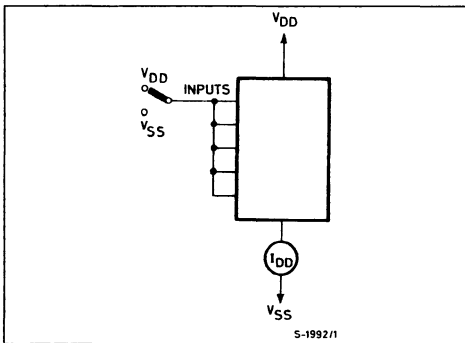
* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

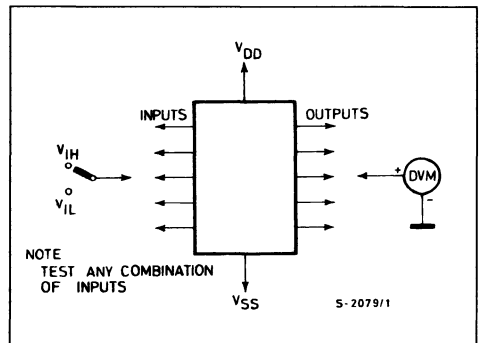
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
CLOCK UP/CLOCK DOWN							
tw	Pulse Width		5		85		ns
			10		35		
			15		15		
fCL	Maximum Frequency		5		2.5		MHz
			10		5		
			15		8		
twC	Carry Pulse Width		5		225		ns
			10		100		
			15		70		
twB	Borrow Pulse Width		5		260		ns
			10		110		
			15		80		
RESET							
tPLH tPHL	Propagation Delay Time Reset to Clock		5		750		ns
			10		285		
			15		200		
	Delay from Reset to First Allowable Clock		5		300		ns
		10		125			
		15		75			
tw	Pulse Width		5		150		ns
			10		60		
			15		40		

TEST CIRCUITS

Quiescent Device Current.

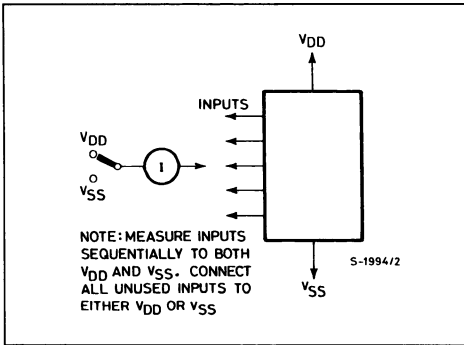


Noise Immunity.



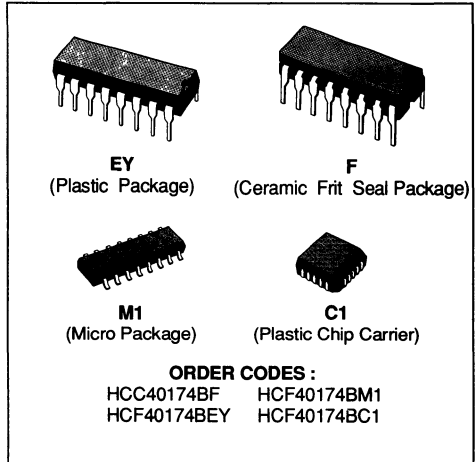
TEST CIRCUITS

Input Leakage Current.



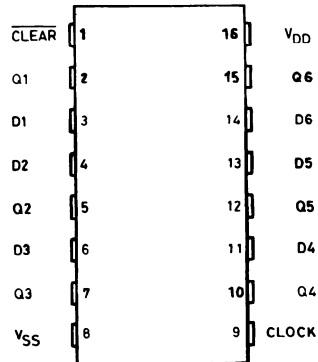
HEX "D" – TYPE FLIP-FLOP

- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18 V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

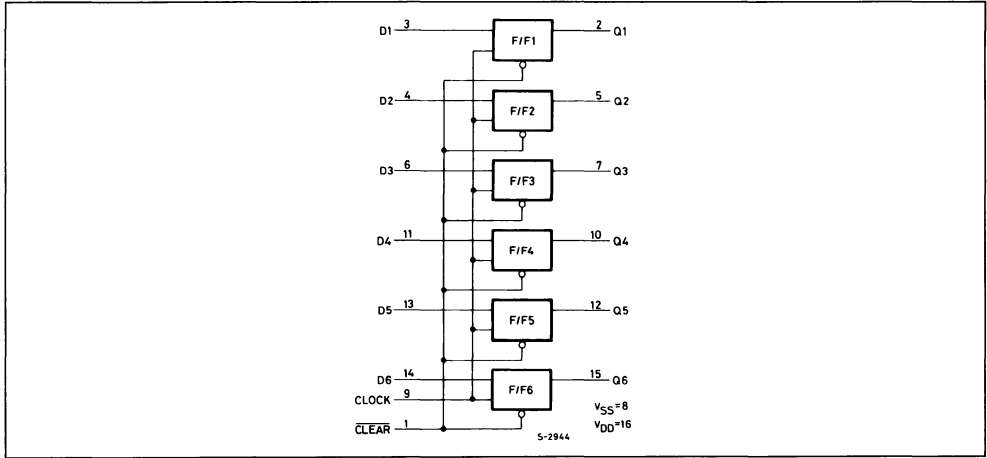
The **HCC40174B** (extended temperature range) and **HCF40174B** (intermediate temperature range) are monolithic integrated circuits available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF40174B** consists of six identical 'D' - type flip-flops having independent DATA inputs. The CLOCK and CLEAR inputs are common to all six units. Data is transferred to the Q outputs on the positive-going transition of the clock pulse. All six flip-flops are simultaneously reset by a low level on the CLEAR input.

PIN CONNECTIONS


5-2936

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

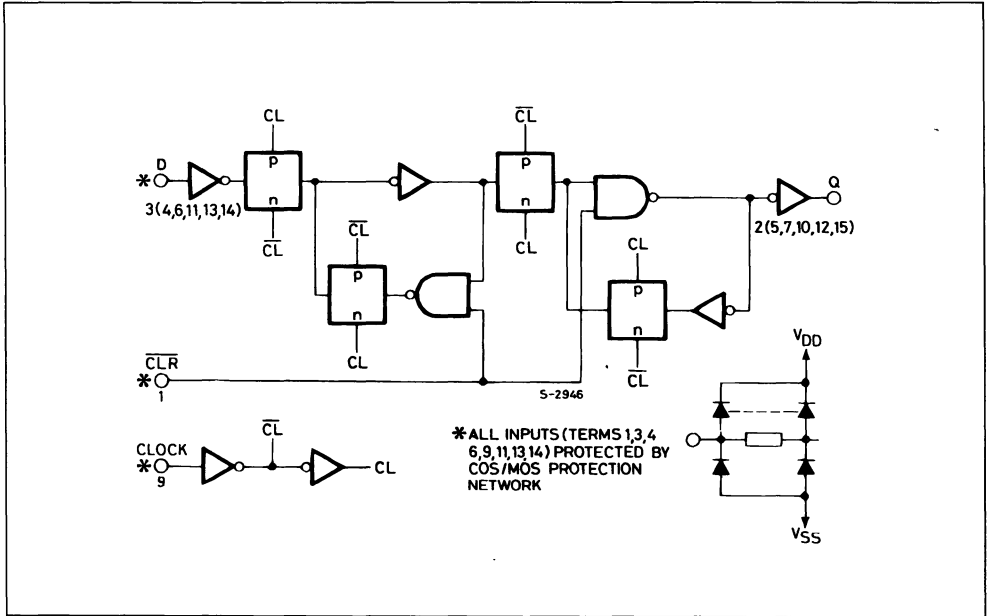
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}\text{C}$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}\text{C}$ $^{\circ}\text{C}$

LOGIC DIAGRAM (1 of 6 Flip-Flops)



TRUTH TABLE

Inputs			Output
Clock	Data	Clear	Q
	0	1	0
	1	1	1
	X	1	NC
X	X	0	0

1 = High Level
0 = Low Level

X = Don't Care
NC = No Change

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5			1	0.02	1		30	μ A
			0/10			10			2	0.02	2		60	
			0/15			15			4	0.02	4		120	
			0/20			20			20	0.04	20		600	
		HCF Types	0/5			5			4	0.02	4		30	
			0/10			10			8	0.02	8		60	
			0/15			15			16	0.02	16		120	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1	\pm 10 ⁻⁵	\pm 0.1			\pm 1	μ A	
		HCF Types	0/15		15		\pm 0.3	\pm 10 ⁻⁵	\pm 0.3		\pm 1			
C _I	Input Capacitance			Any Input				5	7.5			pF		

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.

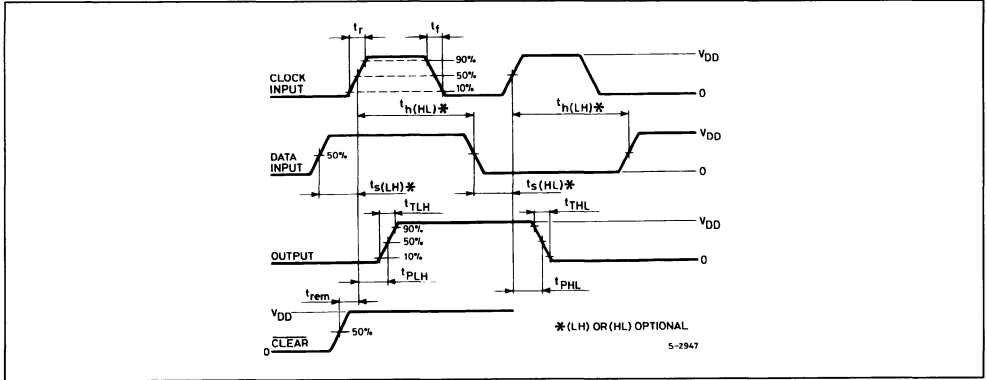
* T_{High} = +125°C for HCC device ; +85°C for HCF device.

The Noise Margin for both "1" and "0" level is \cdot 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V

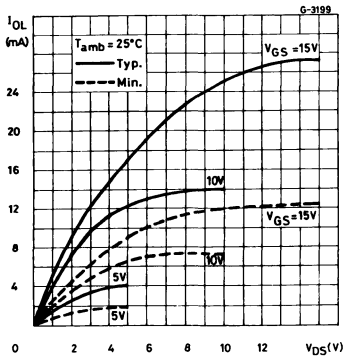
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time Clock to Output		5		150	300	ns
			10		70	140	
			15		50	100	
t_{PHL}	Propagation Delay Time Clear to Output		5		100	200	ns
			10		50	100	
			15		40	80	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{setup}	Data Setup Time		5	40	20		ns
			10	20	10		
			15	10	0		
t_{hold}	Data Hold Time		5	80	40		ns
			10	40	20		
			15	30	15		
t_w	Clock Input Pulse Width Low Level		5	130	65		ns
			10	60	30		
			15	40	20		
t_w	Clock Input Pulse Width High Level		5	130	65		ns
			10	60	30		
			15	40	20		
t_w	$\overline{\text{Clear}}$ Input Pulse Width Low Level		5	100	50		ns
			10	50	25		
			15	40	20		
t_r , t_f	Clock Input Rise or Fall Time		5			15	μs
			10			15	
			15			15	
t_{rem}	Clear Removal Time		5	0	- 40		ns
			10	0	- 15		
			15	0	- 10		
f_{CL}	Maximum Clock Input Frequency		5	3.5	7		MHz
			10	6	12		
			15	8	16		

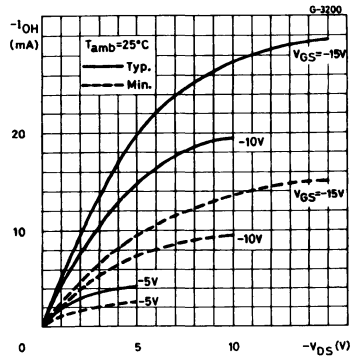
WAVEFORMS



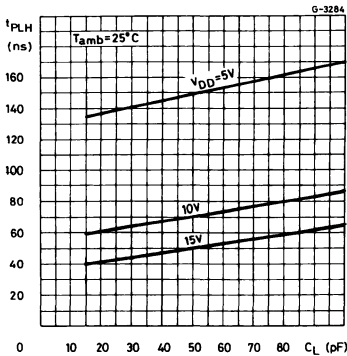
Output Low (sink) Current Characteristics.



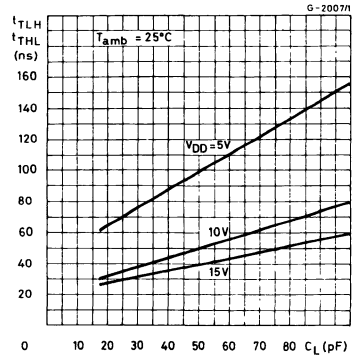
Output High (source) Current Characteristics.



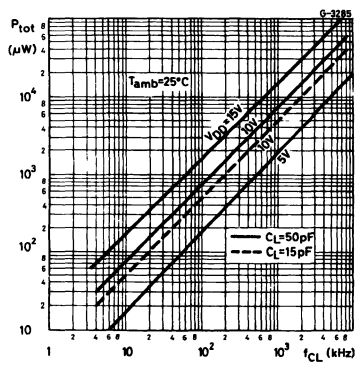
Typical Propagation Delay Time (clock to output) vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

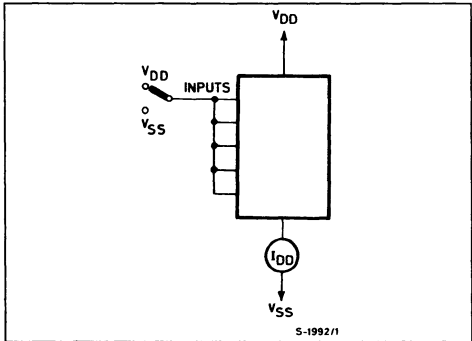


Typical Dynamical Power Dissipation vs. Clock Frequency.

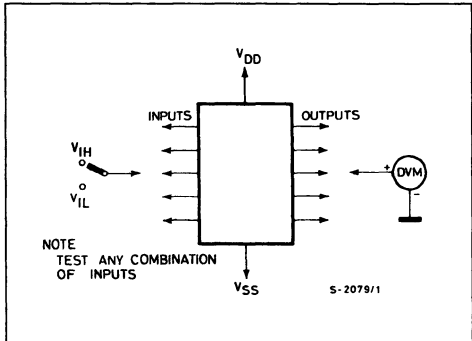


TEST CIRCUITS

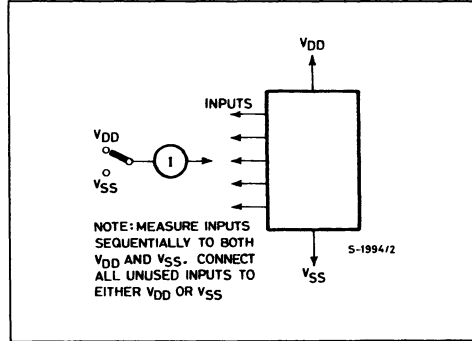
Quiescent Device Current.



Input Voltage.

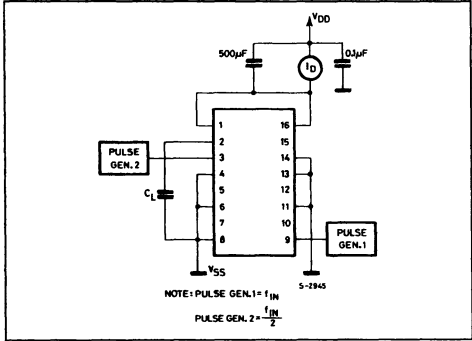


Input Leakage Current.



NOTE: MEASURE INPUTS SEQUENTIALLY TO BOTH VDD AND VSS. CONNECT ALL UNUSED INPUTS TO EITHER VDD OR VSS

Dynamic Power Dissipation.



NOTE: PULSE GEN. 1 = $\frac{1}{2} I_{IN}$
PULSE GEN. 2 = $\frac{1}{2} I_{IN}$



SYNCHRONOUS PROGRAMMABLE 4-BIT COUNTERS

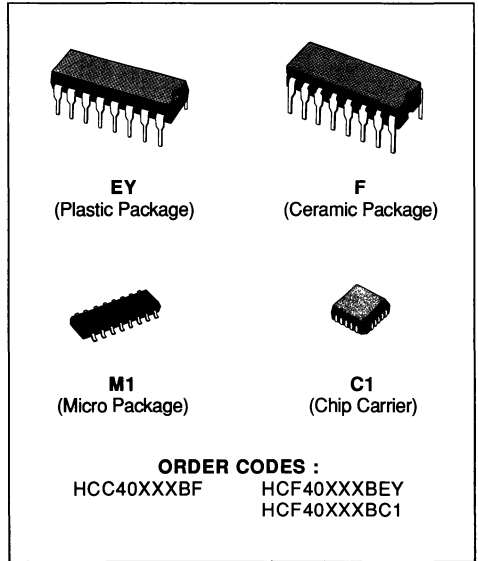
- 40160B - DECADE WITH ASYNCHRONOUS CLEAR**
- 40161B - BINARY WITH ASYNCHRONOUS CLEAR**
- 40162B - DECADE WITH SYNCHRONOUS CLEAR**
- 40163B - BINARY WITH SYNCHRONOUS CLEAR**

- INTERNAL LOOK-AHEAD FOR FAST COUNTING
- CARRY OUTPUT FOR CASCADING
- SYNCHRONOUSLY PROGRAMMABLE
- LOW-POWER TTL COMPATIBILITY
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 250c FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES "

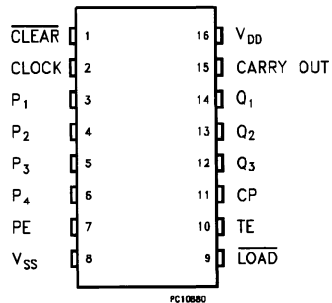
DESCRIPTION

The **HCC40160B, 40161B, 40162B, 40163B** (extended temperature range) and **HCF40160B, 40161B, 40162B, 40163B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in line plastic or ceramic package and plastic micropackage.

HCC/HCF40160B, 40161B, 40162B and **40163B** are 4-bit synchronous programmable counters. The CLEAR function of the **HCC/HCF40162B** and **40163B** is synchronous and a low on the at the clear CLEAR input sets all four outputs low on the next positive CLOCK edge. The CLEAR function of the **HCC/HCF40160B** and **40161B** is asynchronous and a low level at the CLEAR input sets all four outputs low regardless of the state of the CLOCK, LOAD or ENABLE inputs. A low level at the LOAD input disables the counter and causes the output to agree with the set-up data after the next CLOCK pulse regardless of the conditions of the ENABLE inputs. The carry look-ahead circuitry provides for



PIN CONNECTIONS



cascading counter for n-bit synchronous application without additional gating. Instrumental in accomplishing this function are two count-enable input and a carry output (COUT). Counting is enable when both PE and TE inputs are high. The TE input is fed forward to enable COUT. This enable output

produces a positive output pulse with a duration approximately equal to the positive portion of the Q1 output. This positive overflow carry pulse can be used to enable successive cascaded stages. Logic transitions at the PE or TE inputs may occur when the clock is either high or low.

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types	-0.5 to +20	V
	HCF Types	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C







Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types	-55 to +125	°C
	HCF Types	-40 to +85	°C

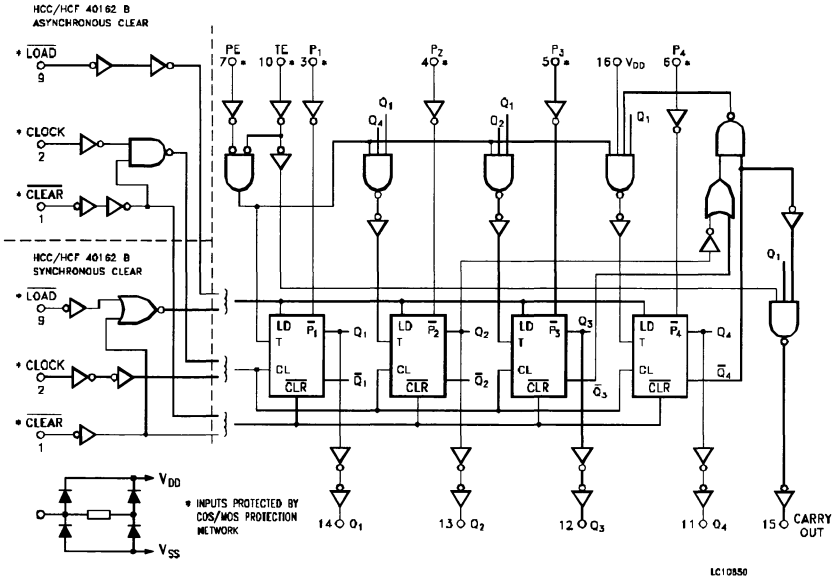
TRUTH TABLE

Clock	CLR	LOAD	PE	TE	Operation
	1	0	X	X	Preset
	1	1	0	X	NC
	1	1	X	0	NC
	1	1	1	1	Count
X	0	X	X	X	Reset (HCC/HCF40160B, HCC/HCF40161B)
	0	X	X	X	Reset (HCC/HCF40162B, HCC/HCF40163B)
	1	X	X	X	NC (HCC/HCF40162B, HCC/HCF40163B)

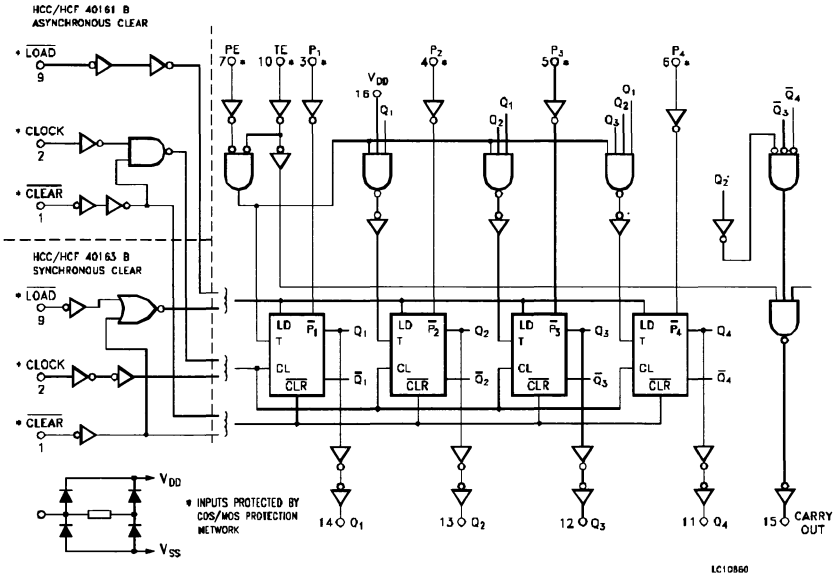
1 = HIGH LEVEL, 0 = LOW LEVEL, X = DON'T CARE, NC = NO CHANGE

LOGIC DIAGRAMS

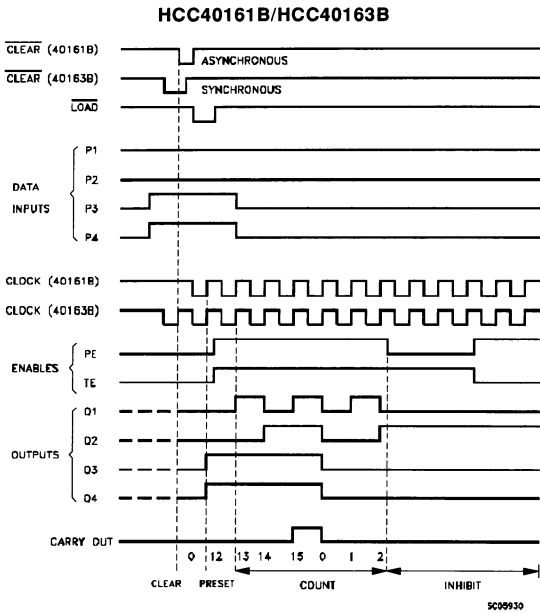
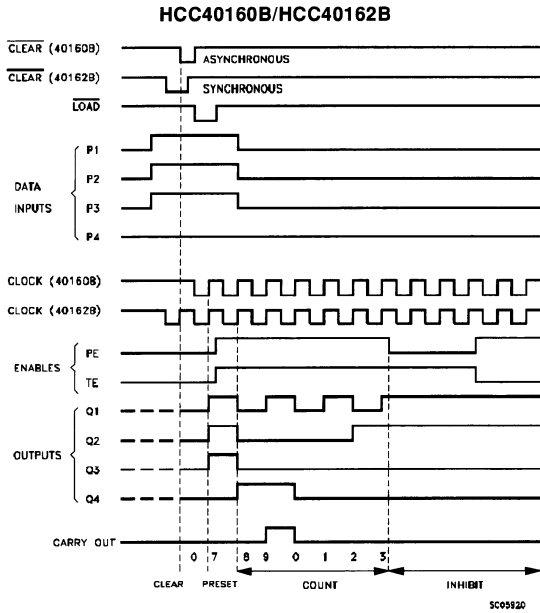
HCC40160B/HCC40162B



HCC40161B/HCC40163B



TIMING DIAGRAMS



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25 °C		T _{HIGH} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5	150	μ A
			0/10			10		10		0.04	10	300	
			0/15			15		20		0.04	20	600	
			0/20			20		100		0.08	100	3000	
		HCF Types	0/5			5		20		0.04	20	150	
			0/10			10		40		0.04	40	300	
			0/15			15		80		0.04	80	600	
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95		V	
		0/10	< 1	10	9.95		9.95			9.95			
		0/15	< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V	
		10/0	< 1	10		0.05			0.05		0.05		
		15/0	< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V	
			1/9	< 1	10	7		7			7		
V _{IL}	Input Low Voltage		1.5/13.5	< 1	15	11		11			11	V	
			4.5/0.5	< 1	5		1.5		1.5		1.5		
			9/1	< 1	10		3		3		3		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36	
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9	
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4	
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1	
			0/5	4.6		5	-0.52		-0.44	-1		-0.36	
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9	
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA
			0/10	0.5		10	1.6		1.3	2.6		0.9	
			0/15	1.5		15	4.2		3.4	6.8		2.4	
		HCF Types	0/5	0.4		5	0.53		0.44	1		0.36	
			0/10	0.5		10	1.3		1.1	2.6		0.9	
			0/15	1.5		15	3.6		3.0	6.8		2.4	
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1	\pm 1	μ A
		HCF Types	0/15			15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3	\pm 1	
C _I	Input Capacitance		Any Input						5	7.5		pF	

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

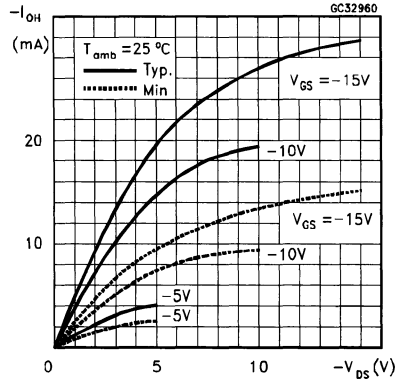
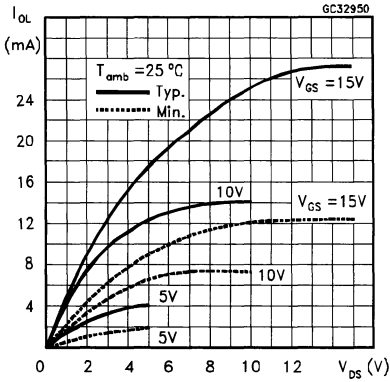
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times= 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time Clock to Q		5		200	400	ns
			10		80	160	
			15		60	120	
t_{PLH} t_{PHL}	Propagation Delay Time Clock to C_{OUT}		5		225	450	ns
			10		95	190	
			15		70	140	
t_{PLH} t_{PHL}	Propagation Delay Time TE to C_{OUT}		5		125	250	ns
			10		55	110	
			15		40	80	
t_{setup}	Setup Time Data to Clock		5	240	120		ns
			10	90	45		
			15	60	30		
t_{setup}	Setup Time Load to Clock		5	240	120		ns
			10	90	45		
			15	60	30		
t_{setup}	Setup Time PE or TE to Clock		5	340	170		ns
			10	140	70		
			15	100	50		
t_{hold}	Hold Time		5	0			ns
			10	0			
			15	0			
t_{rHL} t_{tLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_w	Clock Input Pulse Width		5	170	85		ns
			10	70	35		
			15	50	25		
f_{CL}	Maximum Clock Input Frequency		5	2	3		MHz
			10	5.5	8.5		
			15	8	12		
t_r t_f	Clock Input Rise or Fall Time *					200	ns
						70	
						15	
t_{PHL}	Propagation Delay Time (40160B, 40161B) Clear to Q		5		250	500	ns
			10		110	220	
			15		80	160	
t_{setup}	Setup Time (40162B, 40163B) Clear to Clock		5	340	170		ns
			10	140	70		
			15	100	50		
t_{hold}	Hold Time (40162B, 40163B) Clear to Clock		5	0			ns
			10	0			
			15	0			
t_{rem}	Clear Removal Time (40162B, 40163B)		5	200	100		ns
			10	100	50		
			15	70	35		
t_w	Clear Input Pulse Width Low Level (40160B, 40161B)		5	170	85		ns
			10	70	35		
			15	50	25		

* If more than one unit is cascaded in the parallel clocked application, t_r should be made less than or equal to the sum of the fixed propagation delay at 50 pF and the transition time of the carry output driving stage for the estimated capacitance

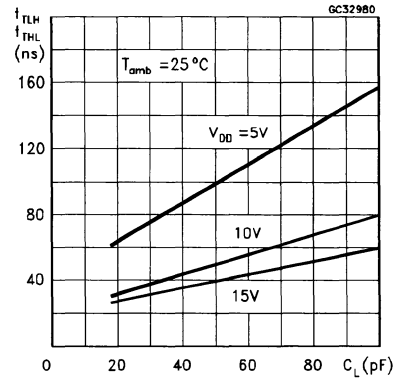
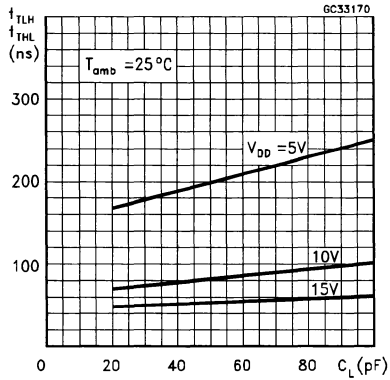
Output Low (sink) Current Characteristics

Output High (source) Current Characteristics

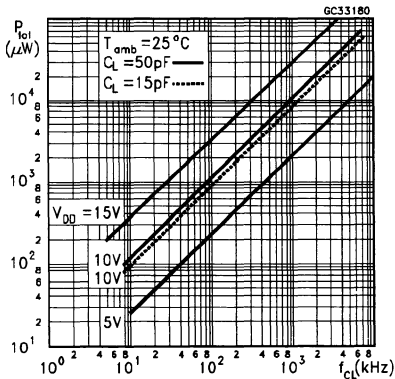


Typical Propagation Delay Time vs Load Capacitance

Typical Transition Time vs Load Capacitance

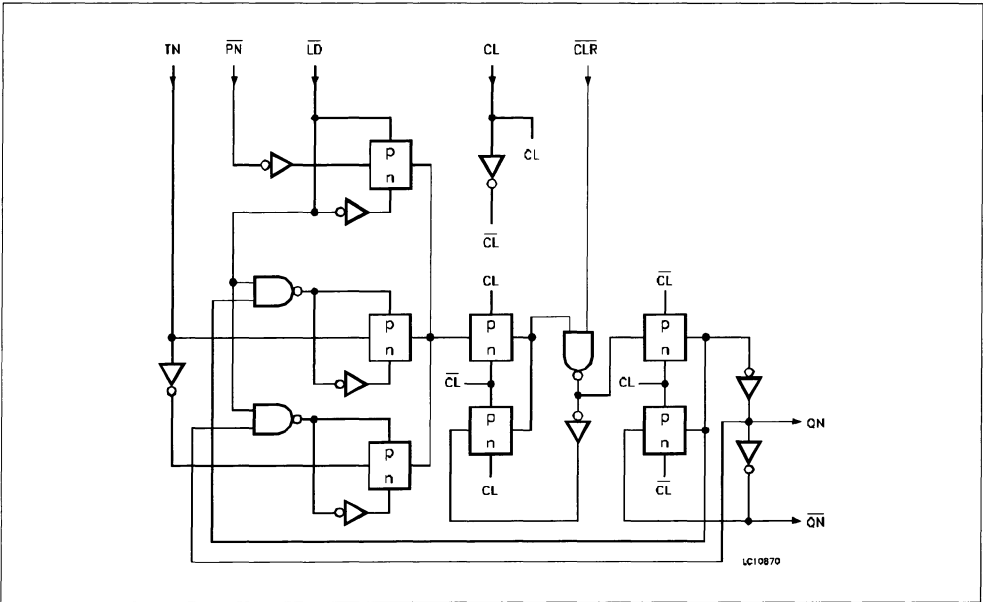


Typical Dynamic Power Dissipation vs Input Frequency

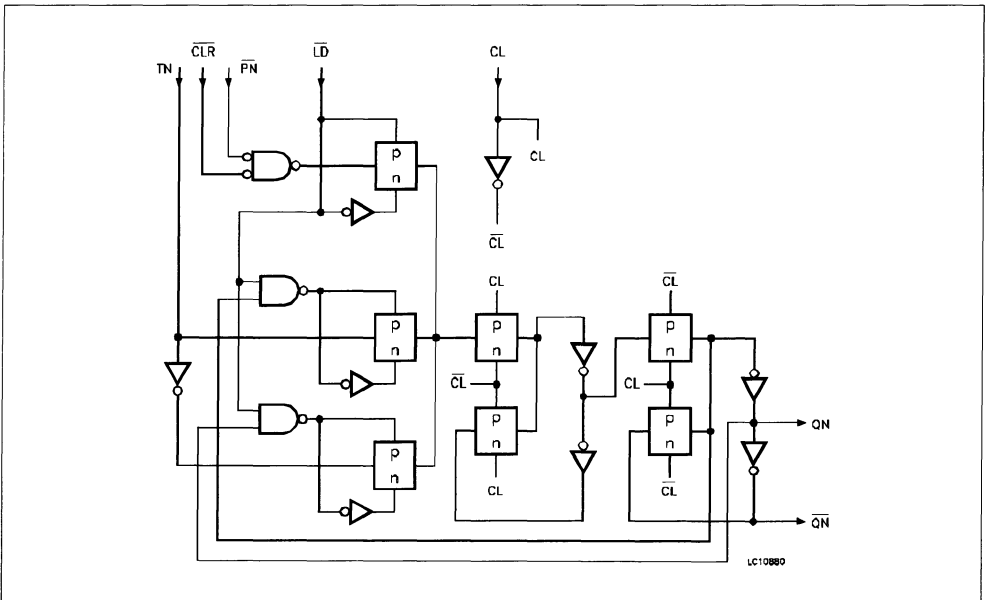


TYPICAL APPLICATIONS

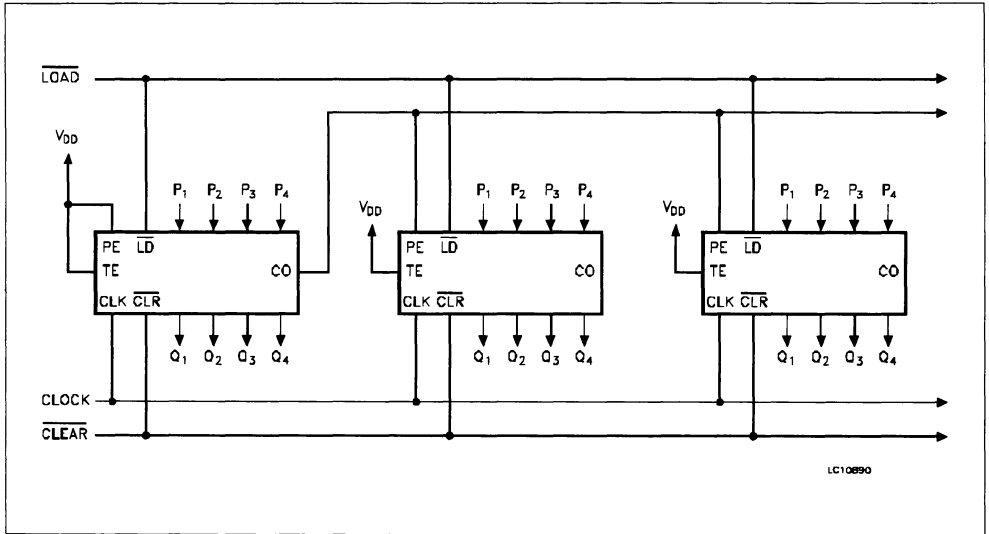
Detail of Flip-flops For 40160B And 40161B (Asynchronous Clear)



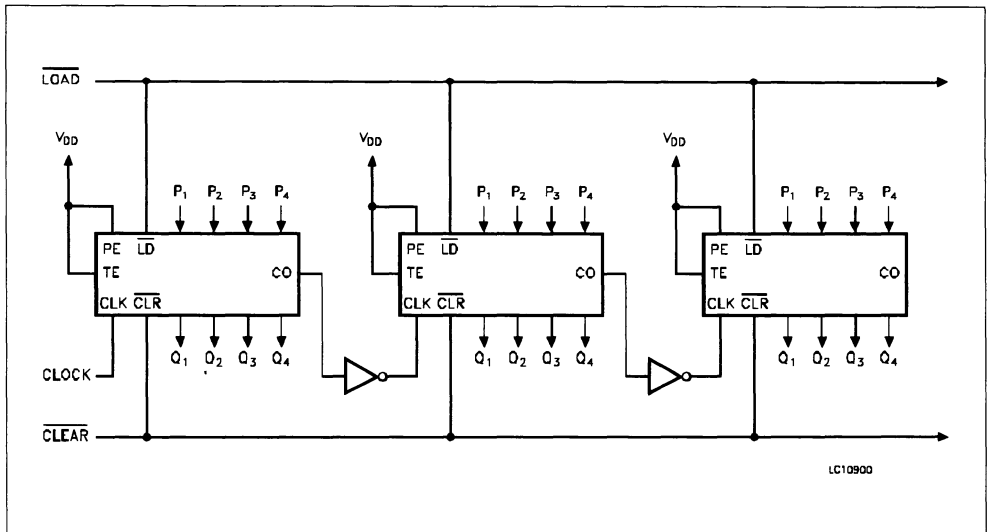
Detail of Flip-flops For 40162B And 40163B (Synchronous Clear)



Cascading Counter Packages In The Parallel-Clocked Mode

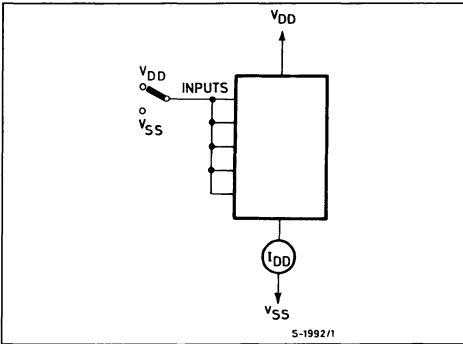


Cascading Counter Packages In The Ripple-Clocked Mode

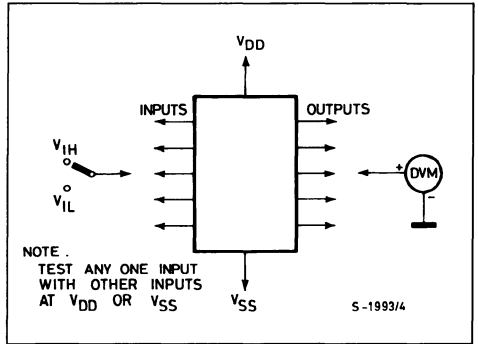


TEST CIRCUIT

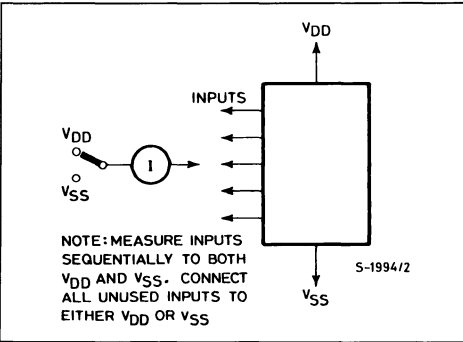
Quiescent Device Current.



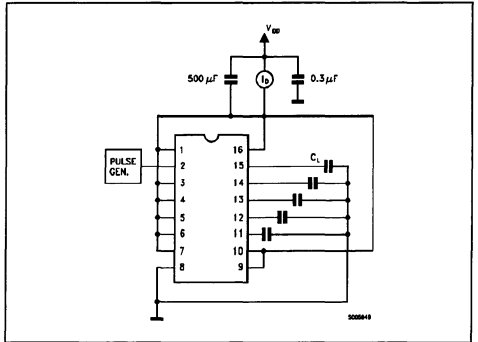
Input Voltage.



Input Leakage Current.



Dynamic Power Dissipation

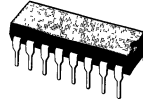


10 TO 4 LINE BCD PRIORITY ENCODER

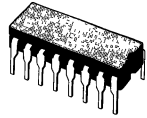
- ENCODES 10 LINE TO 4 LINE BCD
- ACTIVE LOW INPUTS AND OUTPUTS
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERIZATION
- 100 % TESTED FOR QUIESCENT CURRENT AT 20 V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MAXIMUM INPUT CURRENT OF 1 μ A AT 18V OVER FULL PACKAGE TEMPERATURE RANGE; 100 nA AT 18 V AND 25 °C
- NOISE MARGIN (FULL PACKAGE TEMPERATURE RANGE): 1V AT $V_{DD} = 5V$, 2V AT $V_{DD} = 10V$, 2.5V AT $V_{DD} = 15V$

APPLICATIONS:

- KEYBOARD ENCODING
- 10 LINE TO BCD ENCODING
- RANGE SELECTION



EY
(Plastic Package)



F
(Ceramic Package)



M1
(Micro Package)



C1
(Chip Carrier)

ORDER CODES :

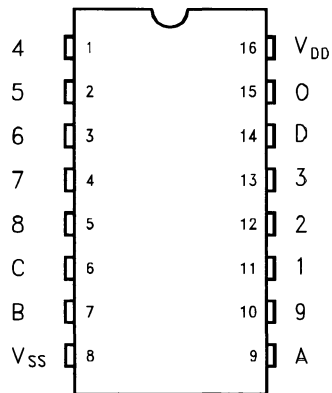
HCC40147BF	HCF40147BM1
HCF40147BEY	HCF40147BC1

DESCRIPTION

The **HCC/HCF40147B** CMOS encoder features priority encoding of the inputs to ensure that only the highest order data line is encoded. Ten data input lines (0-9) are encoded to four line (8, 4, 2, 1) BCD. The highest priority line is line 9. All four output lines are logic 1 (VSS) when all input lines are logic 0. All inputs and outputs are buffered, and each output can drive one TTL Low Power Schottky load. The **HCC/HCF40147** is functionally similar to the T54/T74LS147 if pin 15 is tied low.

The **HCC/HCF40147B** types are supplied in 16 lead plastic or ceramic and plastic micropackage.

PIN CONNECTIONS



PC10870

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20	V
		-0.5 to +18	V
V _i	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

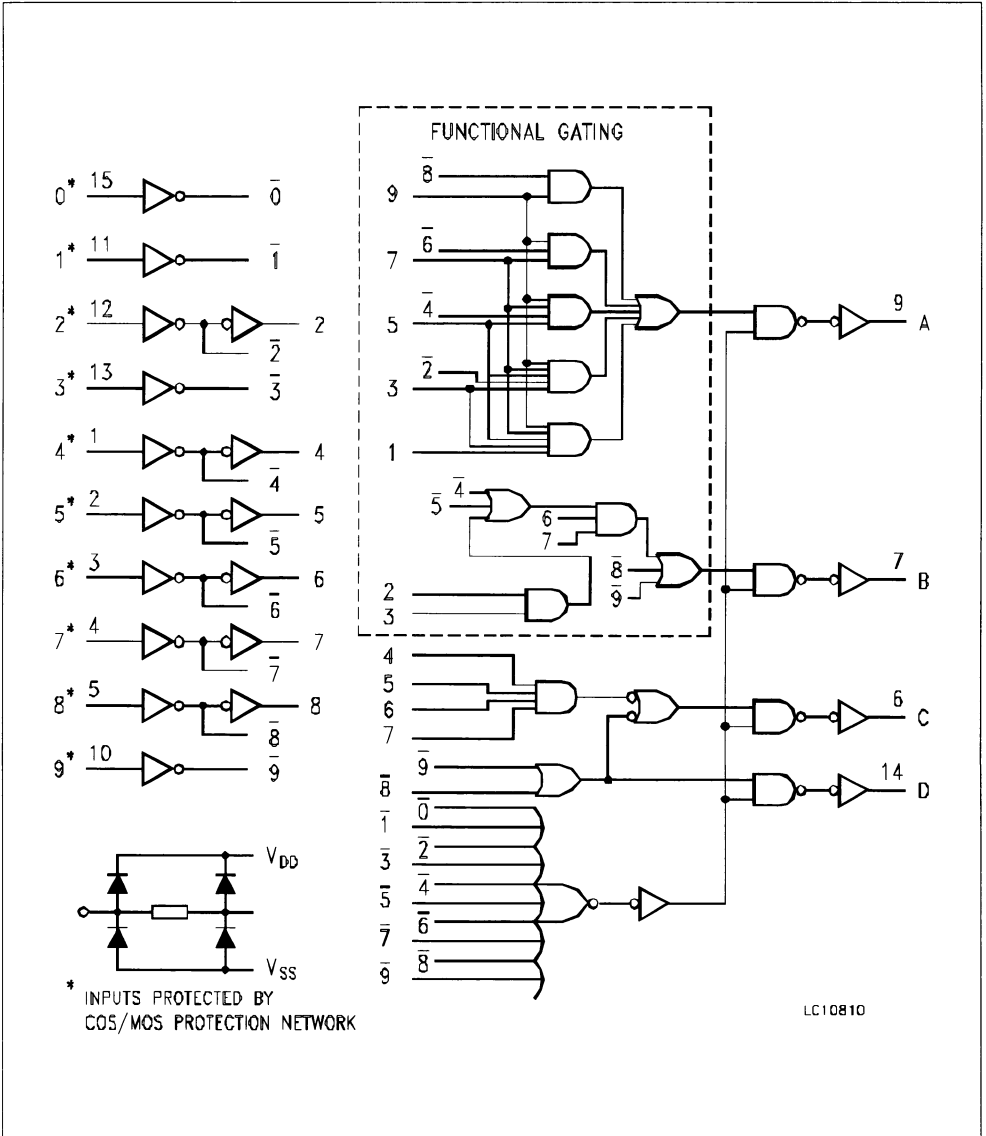
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125	°C
		-40 to +85	°C

TRUTH TABLE

INPUT										OUTPUTS			
0	1	2	3	4	5	6	7	8	9	D	C	B	A
0	0	0	0	0	0	0	0	0	0	1	1	1	1
1	0	0	0	0	0	0	0	0	0	0	0	0	0
X	1	0	0	0	0	0	0	0	0	0	0	0	1
X	X	1	0	0	0	0	0	0	0	0	0	1	0
X	X	X	1	0	0	0	0	0	0	0	0	1	1
X	X	X	X	1	0	0	0	0	0	0	1	0	0
X	X	X	X	X	1	0	0	0	0	0	1	1	0
X	X	X	X	X	X	1	0	0	0	0	1	1	1
X	X	X	X	X	X	X	X	1	0	1	0	0	0
X	X	X	X	X	X	X	X	X	1	1	0	0	1

0 = High Level, 1 = Low Level, X = Don't Care

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

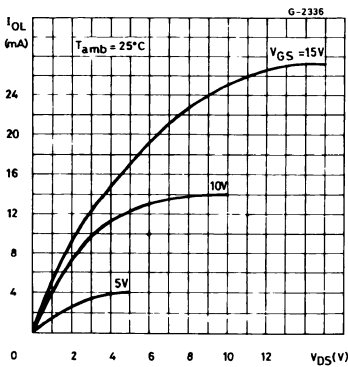
Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25 °C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		1	0.02	1		30	μ A	
			0/10			10		2	0.02	2		60		
			0/15			15		4	0.02	4		120		
			0/20			20		20	0.04	20		600		
		HCF Types	0/5			5		4	0.02	4		30		
			0/10			10		8	0.02	8		60		
0/15				15		16	0.02	16		120				
V _{OH}	Output High Voltage	0/5	< 1	5	4.95		4.95			4.95		V		
		0/10	< 1	10	9.95		9.95			9.95				
		0/15	< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V		
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5			3.5		V		
		1/9	< 1	10	7		7			7				
		1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5			1.5		1.5	V		
		9/1	< 1	10		3			3		3			
		13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2	-1.6	-3.2		-1.15	mA		
			0/5	4.6		5	-0.64	-0.51	-1		-0.36			
			0/10	9.5		10	-1.6	-1.3	-2.6		-0.9			
			0/15	13.5		15	-4.2	-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53	-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52	-0.44	-1		-0.36			
0/10	9.5			10	-1.3	-1.1	-2.6		-0.9					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64	0.51	1		0.36	mA		
			0/10	0.5		10	1.6	1.3	2.6		0.9			
			0/15	1.5		15	4.2	3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52	0.44	1		0.36			
			0/10	0.5		10	1.3	1.1	2.6		0.9			
			0/15	1.5		15	3.6	3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A		
		0/15			15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1	μ A		
C _i	Input Capacitance		Any Input					5	7.5		pF			

* T_{Low} = -55 °C for HCC device -40 °C for HCF device* T_{High} = +125 °C for HCC device +85 °C for HCF deviceThe Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5 V, 2 V min with V_{DD} = 10 V, 2.5 V min with V_{DD} = 15 V

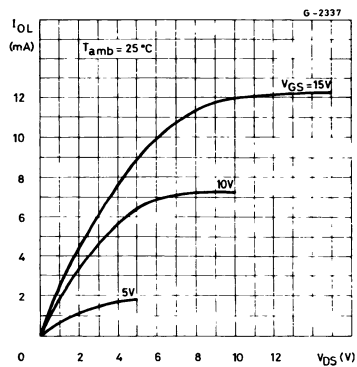
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ } \%/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time In Phase Output		5		450	900	ns
			10		200	400	
			15		150	300	
t_{PLH} t_{PHL}	Propagation Delay Time Out of Phase Output		5		425	850	ns
			10		175	350	
			15		125	250	
t_{TLH} t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
C_i	Input Capacitance				5	7.5	pF

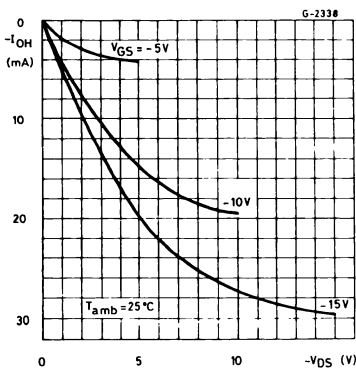
Typical Output Low (source) Current Characteristics



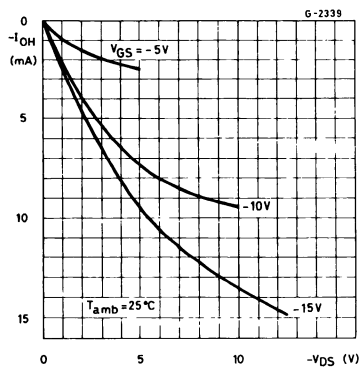
Minimum Output Low (source) Current Characteristics



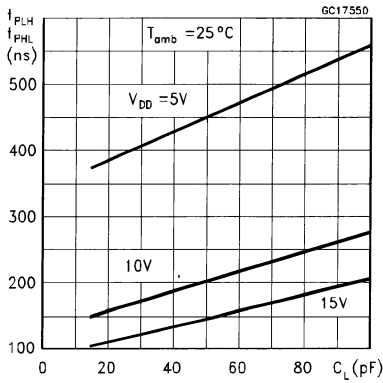
Typical Output High (source) Current Characteristics



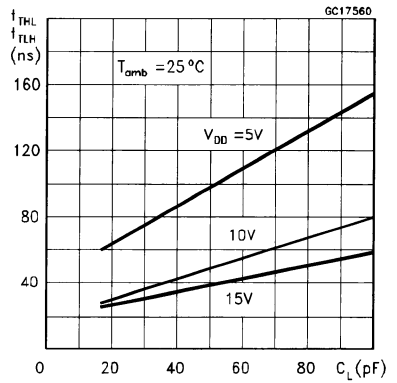
Minimum Output High (source) Current Characteristics



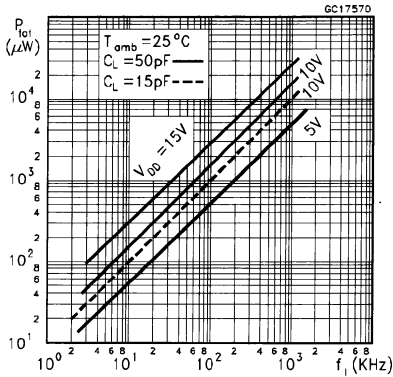
Propagation Delay Time vs Load Capacitance



Typical Transition Time vs Load Capacitance

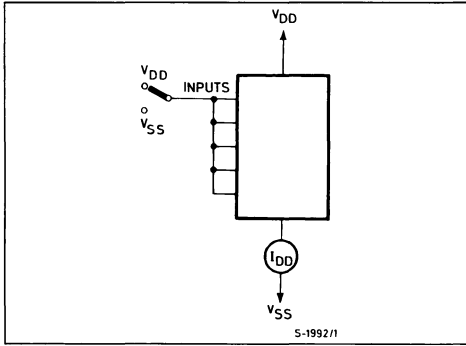


Typical Dynamic Power Dissipation vs Input Frequency

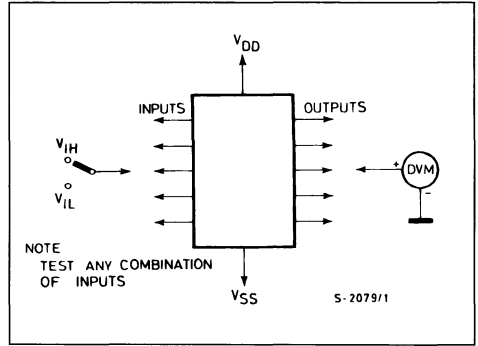


TEST CIRCUITS

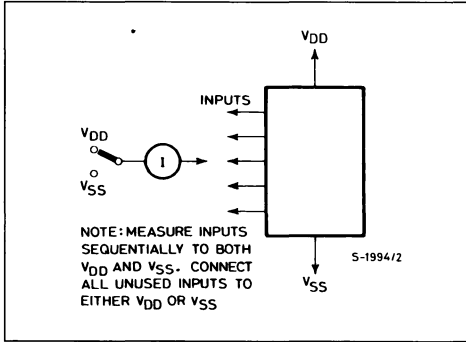
Quiescent Device Current.



Noise Immunity.

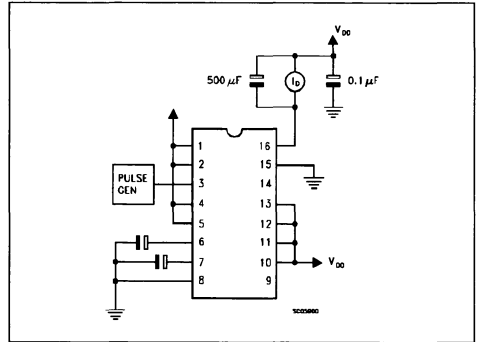


Input Leakage Current.



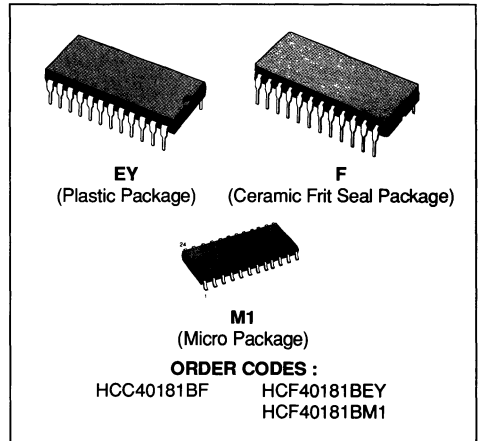
NOTE: MEASURE INPUTS SEQUENTIALLY TO BOTH V_{DD} AND V_{SS}. CONNECT ALL UNUSED INPUTS TO EITHER V_{DD} OR V_{SS}

Dynamic Power Dissipation Test Circuit

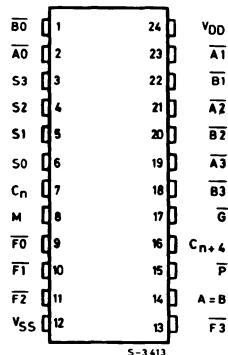


4-BIT ARITHMETIC LOGIC UNIT

- FULL LOOK-AHEAD CARRY FOR SPEED OPERATIONS ON LONG WORDS
- GENERATES 16 LOGIC FUNCTIONS OF TWO BOOLEAN VARIABLES
- GENERATES 16 ARITHMETIC FUNCTIONS OF TWO 4-BIT BINARY WORDS
- A = B COMPARATOR OUTPUT AVAILABLE
- RIPPLE-CARRY INPUT AND OUTPUT AVAILABLE
- TYPICAL ADDITION TIME 200ns @ $V_{DD} = 10V$
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"


DESCRIPTION

The **HCC40181B** (extended temperature range) and **HCF40181B** (intermediate temperature range) are monolithic integrated circuits, available in 24-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF40181B** is a low-power four-bit parallel arithmetic logic unit (ALU) capable of providing 16 binary arithmetic operations on two four-bit words and 16 logical functions of two Boolean variables. The mode control input M selects logical (M = High) or arithmetic (M = Low) operation. The four select inputs (S0, S1, S2, and S3) select the desired logical or arithmetic functions, which include AND, OR, NAND, NOR, and exclusive-OR and-NOR in the logical mode, and addition, subtraction, decrement, left-shift and straight transfer in the arithmetic mode, according to the truth table. The **HCC/HCF40181B** operation may be interpreted with either active-low or active-high data at the A and B word inputs and the function outputs F, by using the appropriate truth table. The **HCC/HCF40181B** contains logic for full look-ahead carry operation for fast carry generation using the carry-generate and carry-propagate outputs G and

PIN CONNECTIONS


HCC/HCF40181B

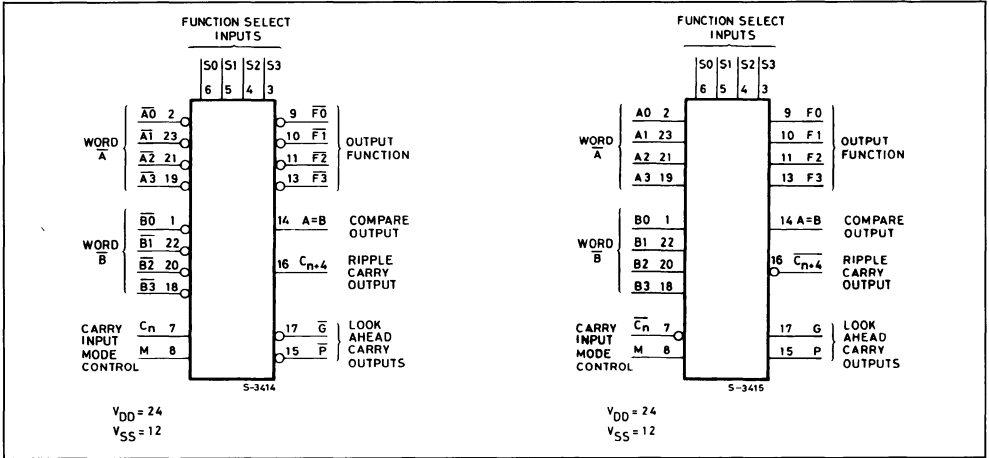
\overline{P} for the four bits of the **HCC/HCF40181B**. Use of the **HCC/HCF40182B** look-ahead carry generator in conjunction with multiple **HCC/HCF40181B**'s permits high-speed arithmetic operations on long words. A ripple carry output C_{n+4} is available for use in systems where speed is not of primary importance. Also included in the **HCC/HCF40181B** is a comparator output $A = B$, which assumes a high

level whenever the two four-bit input words A and B are equal and the device is in the subtract mode. In addition, relative magnitude information may be derived from the carry-in input C_n and ripple carry-out output C_{n+4} by placing the unit in the subtract mode and externally decoding using the information in table II. The **HCC/HCF40181B** is similar to industry types MC 14581 and 74181.

FUNCTIONAL DIAGRAM

Active-low Data.

Active-high Data.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$ $^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltages are with respect to V_{SS} (GND)

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

TRUTH TABLES

Table 1.

Function Select				Inputs/Outputs Active Low		Inputs/Outputs Active High	
				Logic Function (M = H)	Arithmetic* Function (M = L, C _n = L)	Logic Function (M = H)	Arithmetic* Function (M = L, C _n = H)
S3	S2	S1	S0				
0	0	0	0	\overline{A}	A minus 1	\overline{A}	A
0	0	0	1	\overline{AB}	AB minus 1	$\overline{A+B}$	A + B
0	0	1	0	$\overline{A+B}$	AB minus 1	\overline{AB}	A + \overline{B}
0	0	1	1	Logic 1	minus 1	Logic 0	minus 1
0	1	0	0	$\overline{A+B}$	A plus (A + \overline{B})	\overline{AB}	A plus \overline{AB}
0	1	0	1	\overline{B}	AB plus (A + \overline{B})	\overline{B}	(A + B) plus \overline{AB}
0	1	1	0	$\overline{A \oplus B}$	A minus B minus 1	$A \oplus B$	A minus B minus 1
0	1	1	1	$\overline{A + \overline{B}}$	A + \overline{B}	\overline{AB}	\overline{AB} minus 1
1	0	0	0	\overline{AB}	A plus (A + B)	$\overline{A+B}$	A plus AB
1	0	0	1	$\overline{A \oplus B}$	A plus B	$\overline{A \oplus B}$	A plus B
1	0	1	0	\overline{B}	\overline{AB} plus (A + B)	\overline{B}	(A + \overline{B}) plus AB
1	0	1	1	$\overline{A+B}$	A + B	AB	AB minus 1
1	1	0	0	Logic 0	A plus A	Logic 1	A plus A
1	1	0	1	\overline{AB}	AB plus A	$\overline{A + \overline{B}}$	(A + B) plus A
1	1	1	0	AB	\overline{AB} plus A	A + B	(A + \overline{B}) plus A
1	1	1	1	A	A	A	A minus 1

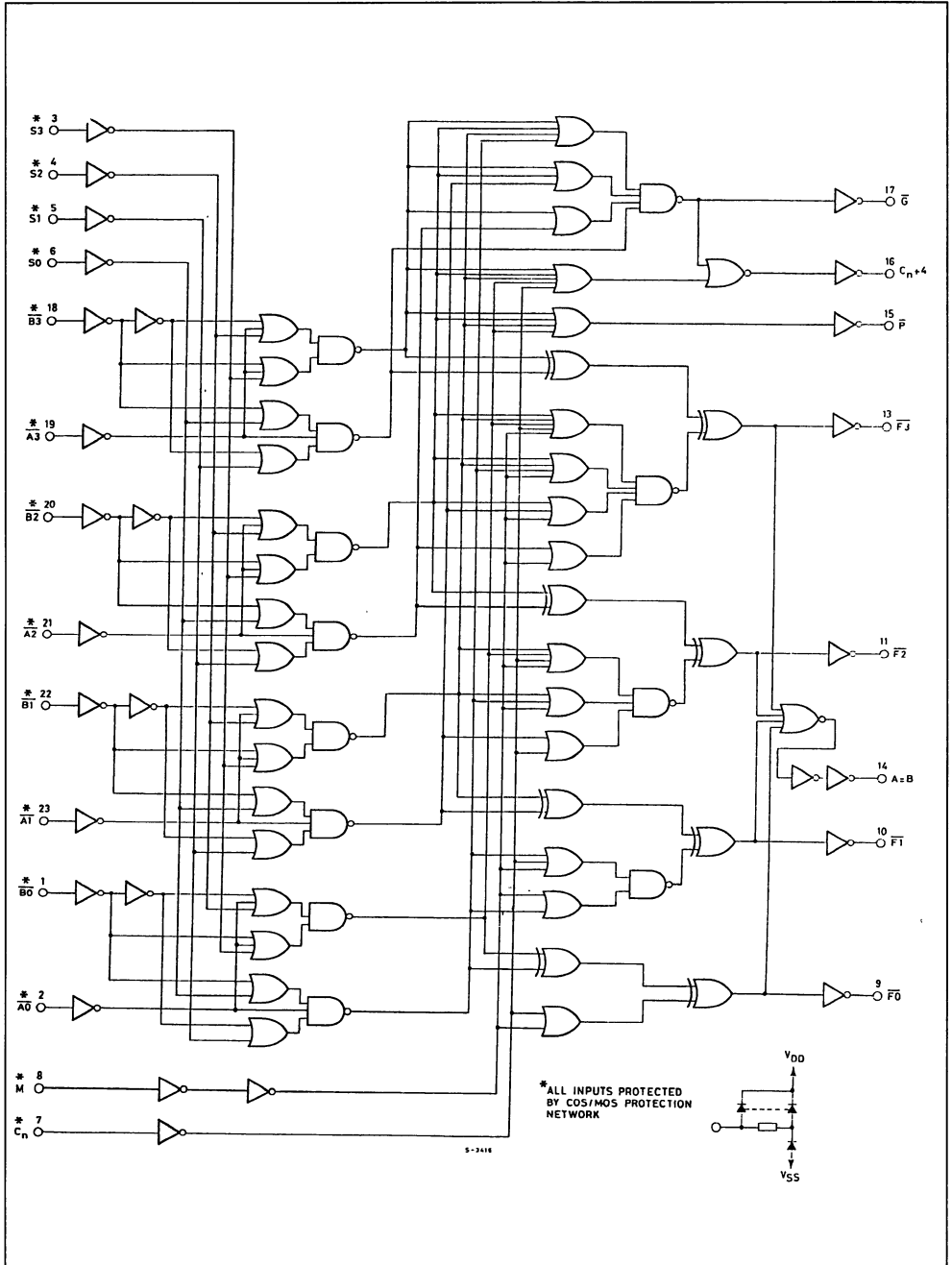
* Expressed as two's complement. For arithmetic function with C_n in the opposite state, the resulting function is as show plus 1.
1 = HIGH LEVEL.
0 = LOW LEVEL.

Table 2 : Magnitude Comparison.

Active-high Data			Active-low Data		
Input C _n	Output C _{n+4}	Magnitude	Input C _n	Output C _{n+4}	Magnitude
1	1	A ≤ B	0	0	A ≤ B
0	1	A < B	1	0	A < B
1	0	A > B	0	1	A > B
0	0	A ≥ B	1	1	A ≥ B

1 = HIGH LEVEL
0 = LOW LEVEL

LOGIC DIAGRAM Active-low Data



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
	HCF Types	0/5			5		20		0.04	20		150		
		0/10			10		40		0.04	40		300		
		0/15			15		80		0.04	80		600		
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage	0.5/4.5	< 1	5	3.5		3.5				3.5		V	
		1/9	< 1	10	7		7				7			
		1.5/13.5	< 1	15	11		11				11			
V _{IL}	Input Low Voltage	4.5/0.5	< 1	5		1.5				1.5		1.5	V	
		9/1	< 1	10		3				3		3		
		13.5/1.5	< 1	15		4				4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4					
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15		15		\pm 0.3		\pm 10 ⁻⁵	\pm 0.3		\pm 1		
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

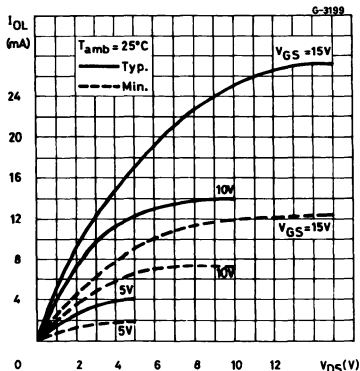
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time A or B to F (logic mode) A or B to G or P		5		400	800	ns
			10		160	320	
			15		120	240	
	A or B to F, C_{n+4} , or A = B		5		300	1000	ns
			10		200	400	
			15		140	280	
	C_n to F		5		320	640	ns
			10		135	270	
			15		100	200	
	C_n to C_{n+4}		5		200	400	ns
			10		100	200	
			15		70	140	
t_{TLH} , t_{THL}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

Table 3 : AC Test Setup Reference (active-low data).

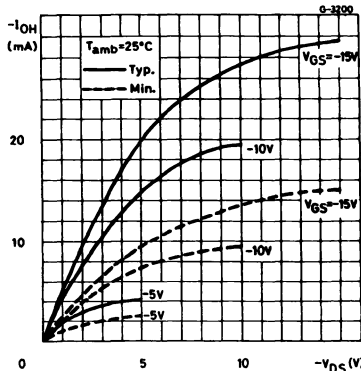
Test Delay Times	AC Paths		DC Data Inputs		Mode*
	Inputs	Outputs	to V_{SS}	to V_{DD}	
SUM _{IN} to SUM _{OUT}	$\overline{B0}$	Any \overline{F}	$\overline{B1}, \overline{B2}, \overline{B3},$ M, C_n	All \overline{A} 's	ADD
SUM _{IN} to P	$\overline{A0}$	\overline{P}	$\overline{A1}, \overline{A2}, \overline{A3},$ M, C_n	All \overline{B} 's	ADD
SUM _{IN} to \overline{G}	$\overline{B0}$	\overline{G}	All \overline{A} 's M, C_n	$\overline{B1}, \overline{B2}, \overline{B3}$	ADD
SUM _{IN} to C_{n+4}	$\overline{B0}$	C_{n+4}	All \overline{A} 's, M, C_n	$\overline{B1}, \overline{B2}, \overline{B3}$	ADD
C_n to SUM _{OUT}	C_n	Any \overline{F}	All \overline{A} 's, M	All \overline{B} 's	ADD
C_n to C_{n+4}	C_n	C_{n+4}	All \overline{A} 's, M	All \overline{B} 's	ADD
SUM _{IN} to A = B	$\overline{B0}$	A = B	All \overline{A} 's $\overline{B1}, \overline{B2}, \overline{B3},$ M	C_n	SUBTRACT
SUM _{IN} to SUM _{OUT} (logic mode)	All \overline{B} 's	Any \overline{F}	All \overline{A} 's, C_n	M	EXCLUSIVE OR

* ADD Mode : S0, S3 = V_{DD} ; S1, S2 = V_{SS} SUBTRACT Mode : S0, S3 = V_{SS} , S1, S2 = V_{DD} .

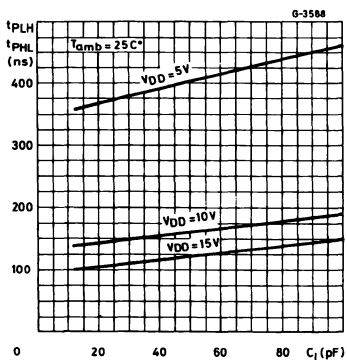
Output Low (sink) Current Characteristics.



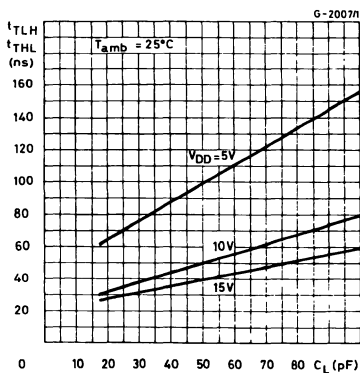
Output High (source) Current Characteristics.



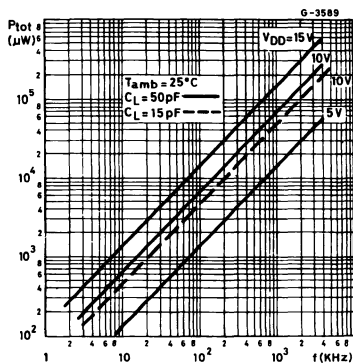
Typical Propagation Delay Time vs. Load Capacitance (for A or B to F, logic mode).



Typical Transition Time vs. Load Capacitance.

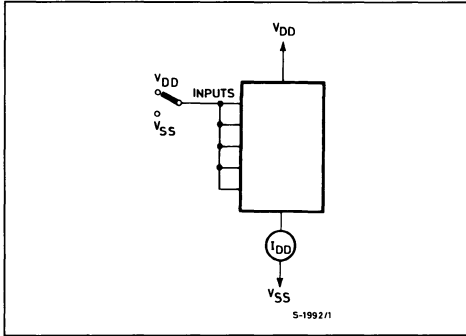


Typical Dynamic Power Dissipation vs. Input Frequency.

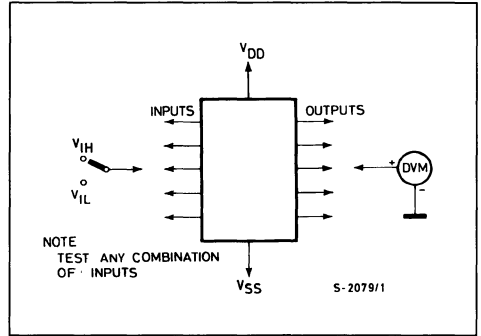


TEST CIRCUITS

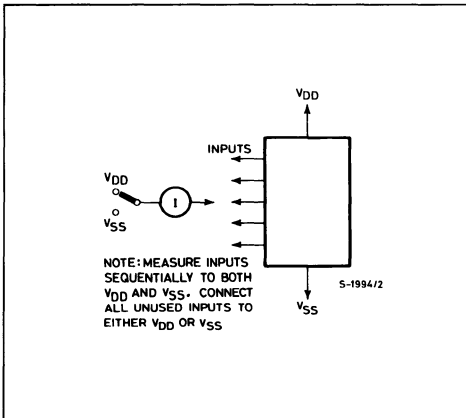
Quiescent Device Current.



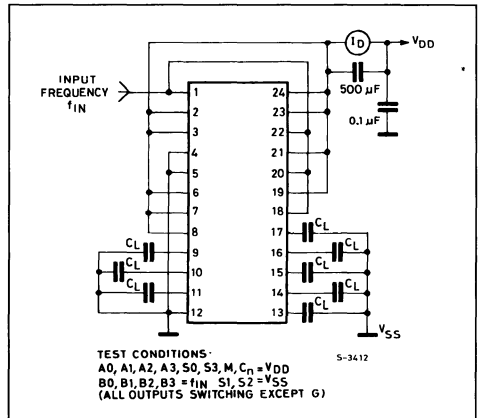
Input Voltage.



Input Leakage Current.

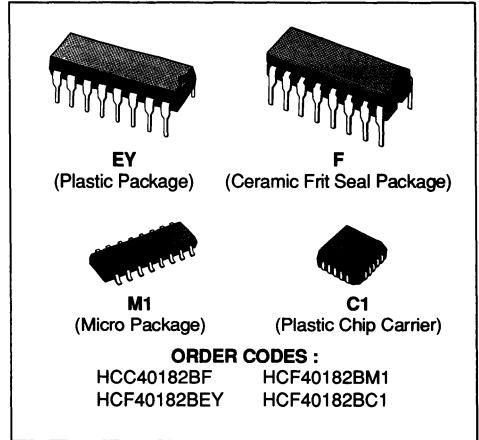


Dynamic Power Dissipation.



LOOK-AHEAD CARRY GENERATOR

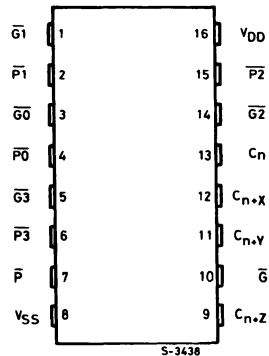
- GENERATES HIGH-SPEED CARRY ACROSS FOUR ADDERS OF ADDER GROUPS
- HIGH-SPEED OPERATIONAL : $t_{PHL} = t_{PLH} = 100\text{ns}$ (typ.) @ $V_{DD} = 10\text{V}$
- CASCADABLE FOR FAST CARRIES OVER N BITS
- DESIGNED FOR USE WITH **HCC/HCF40181B** ALU
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



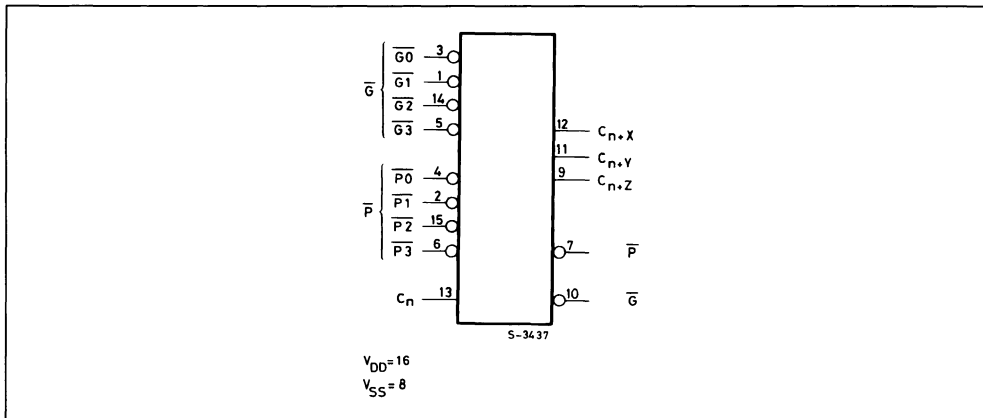
DESCRIPTION

The **HCC40182B** (extended temperature range) and **HCF40182B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF40182B** is a high-speed look-ahead carry generator capable of anticipating a carry across four binary adders or groups of adders. The **HCC/HCF40182B** is cascadeable to perform full look-ahead across n-bit adders. Carry, propagate-carry, and generate-carry functions are provided as enumerated in the terminal designation below. The **HCC/HCF40182B**, when used in conjunction with the **HCC/HCF40181B** arithmetic logic unit (ALU), provides full high-speed look-ahead carry capability for up to n-bit words. Each **HCC/HCF40182B** generates the look-ahead (anticipated carry) across a group of four ALU's. In addition, other **HCC/HCF40182B**'s may be employed to anticipate the carry across sections of four look-ahead blocks up to n-bits. Carry inputs and outputs of the **HCC/HCF40181B** are active-high logic, and carry-generate (G) and carry-propagate (P) outputs are active low. Therefore the inputs and outputs of the **HCC/HCF40182B** are compatible. The **HCC/HCF40182B** is similar to industry type MC14582.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



TERMINAL DESIGNATIONS TABLE

Pin Name	Pin	Function
$\overline{G0}, \overline{G1}, \overline{G2}, \overline{G3}$	3, 1, 14, 5	Active-low Carry-generate Inputs
$\overline{P0}, \overline{P1}, \overline{P2}, \overline{P3}$	4, 2, 15, 6	Active-low Carry-propagate Inputs
C_n	13	Active-high Carry Input
$C_{n+X}, C_{n+Y}, C_{n+Z}$	12, 11, 9	Active-high Carry Outputs
\overline{G}	10	Active-low Group Carry-generate Output
\overline{P}	7	Active-low Group Carry-propagate Output

ABSOLUTE MAXIMUM RATINGS

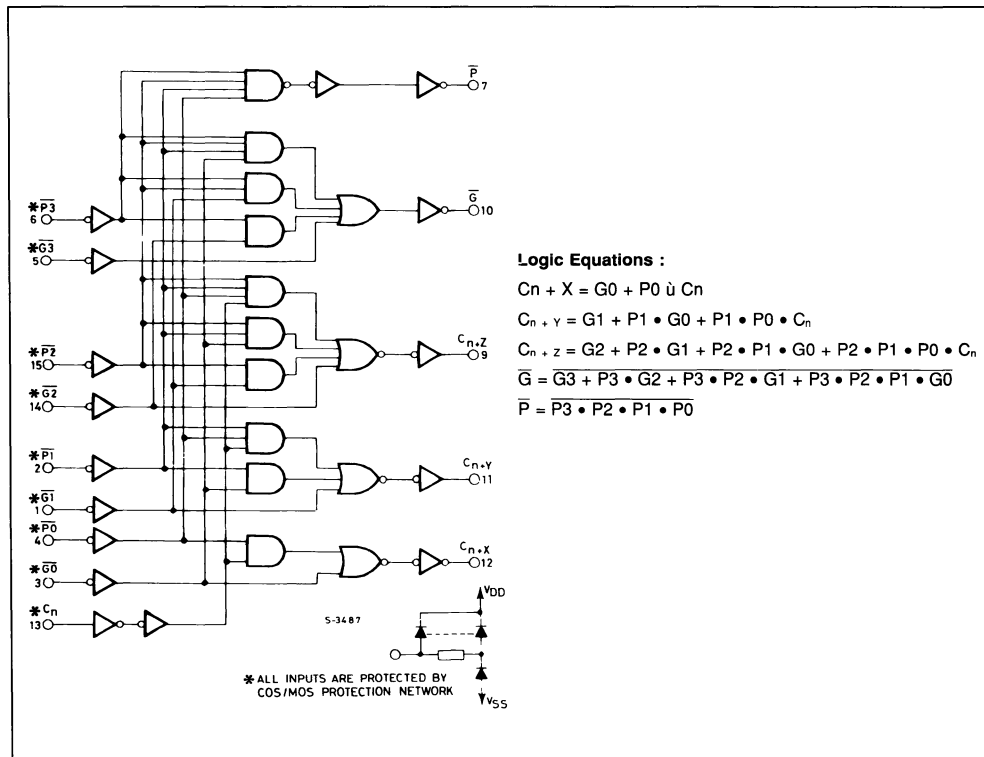
Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V
V_i	Input Voltage	- 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op} =$ Full Package-temperature Range	200 100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	$^{\circ}C$
T_{stg}	Storage Temperature	- 65 to + 150	$^{\circ}C$

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types	3 to 18	V
	HCF Types	3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types	- 55 to + 125	°C
	HCF Types	- 40 to + 85	°C

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/ 5			5		5	0.04	5		150	μ A	
			0/10			10		10	0.04	10		300		
			0/15			15		20	0.04	20		600		
			0/20			20		100	0.08	100		3000		
		HCF Types	0/ 5			5		20	0.04	20		150		
			0/10			10		40	0.04	40		300		
			0/15			15		80	0.04	80		600		
V _{OH}	Output High Voltage	0/ 5	< 1	5	4.95		4.95	5		4.95		V		
		0/10	< 1	10	9.95		9.95	10		9.95				
		0/15	< 1	15	14.95		14.95	15		14.95				
V _{OL}	Output Low Voltage	5/0	< 1	5		0.05			0.05		0.05	V		
		10/0	< 1	10		0.05			0.05		0.05			
		15/0	< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V		
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5		1.5		1.5	V		
			9/1	< 1	10		3		3		3			
			13.5/1.5	< 1	15		4		4		4			
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2	- 1.6	- 3.2		- 1.15	mA		
			0/ 5	4.6		5	- 0.64	- 0.51	- 1		- 0.36			
			0/10	9.5		10	- 1.6	- 1.3	- 2.6		- 0.9			
			0/15	13.5		15	- 4.2	- 3.4	- 6.8		- 2.4			
		HCF Types	0/ 5	2.5		5	- 1.53	- 1.36	- 3.2		- 1.1			
			0/ 5	4.6		5	- 0.52	- 0.44	- 1		- 0.36			
			0/10	9.5		10	- 1.3	- 1.1	- 2.6		- 0.9			
0/15	13.5		15	- 3.6	- 3.0	- 6.8		- 2.4						
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64	0.51	1		0.36	mA		
			0/10	0.5		10	1.6	1.3	2.6		0.9			
			0/15	1.5		15	4.2	3.4	6.8		2.4			
		HCF Types	0/ 5	0.4		5	0.52	0.44	1		0.36			
			0/10	0.5		10	1.3	1.1	2.6		0.9			
			0/15	1.5		15	3.6	3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1	$\pm 10^{-5}$	\pm 0.1		\pm 1	μ A		
		HCF Types	0/15		15		\pm 0.3	$\pm 10^{-5}$	\pm 0.3		\pm 1			
C _I	Input Capacitance		Any Input					5	7.5		pF			

* T_{Low} = - 55°C for HCC device : - 40°C for HCF device.

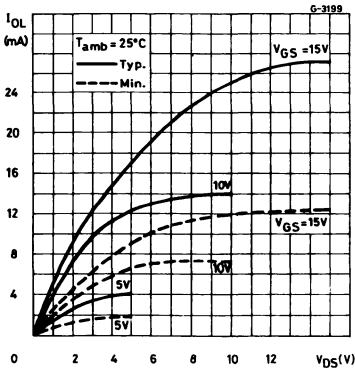
* T_{High} = + 125°C for HCC device : + 85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

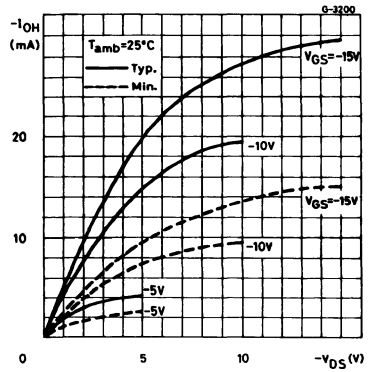
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time P, G, in to P G Out and Carry Outs	5			200	400	ns
		10			100	200	
		15			75	150	
	C_n to Carry Outs	5			240	480	ns
		10			120	240	
		15			90	180	
t_{THL} t_{TLH}	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

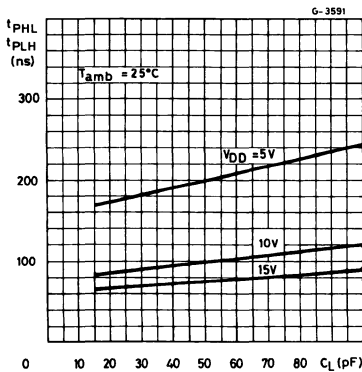
Output Low (sink) Current Characteristics.



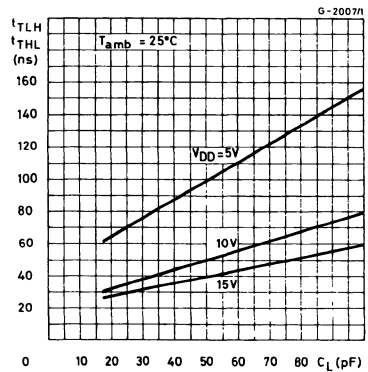
Output High (source) Current Characteristics.



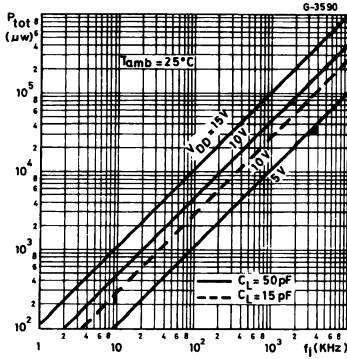
Typical Propagation Delay Time (P, G In to P, G Out and Carry-outs) vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

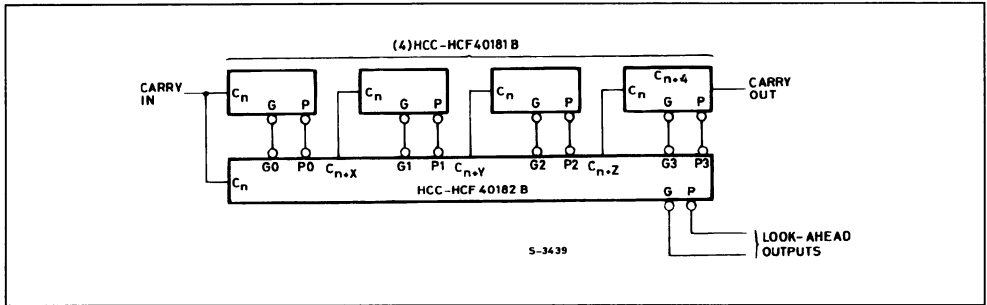


Typical Dynamic Power Dissipation vs. Input Frequency.

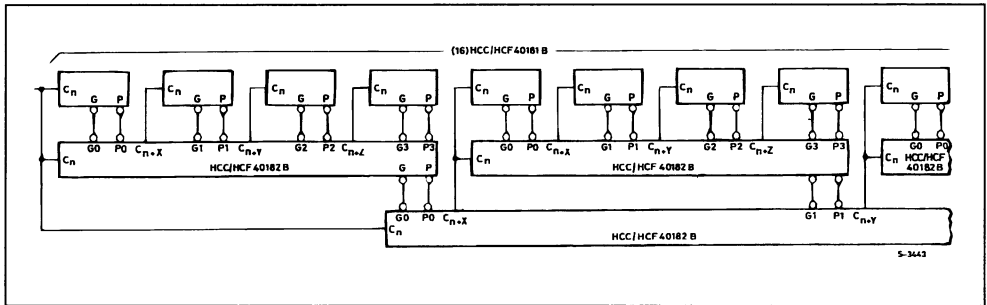


TYPICAL APPLICATIONS

16-BIT TWO-LEVEL LOOK-AHEAD ALU

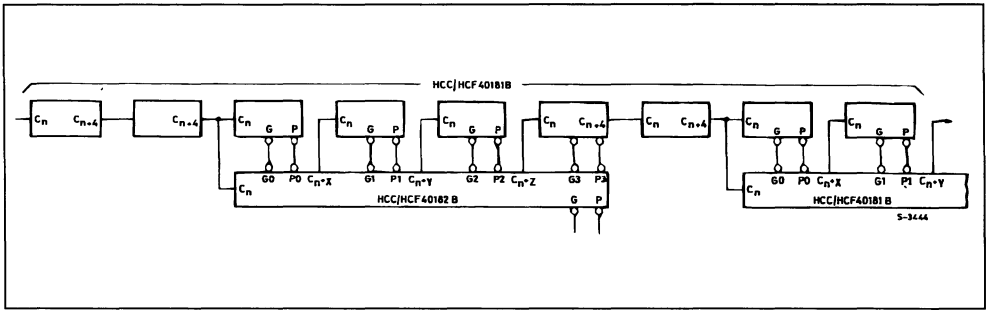


64-BIT FULL CARRY LOOK-AHEAD ALU IN 3 LEVELS



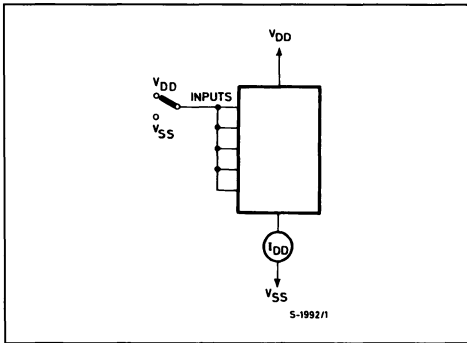
TYPICAL APPLICATIONS (continued)

COMBINED TWO-LEVEL LOOK-AHEAD AND RIPPLE-CARRY ALU

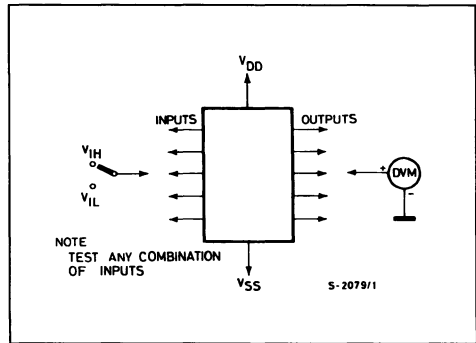


TEST CIRCUITS

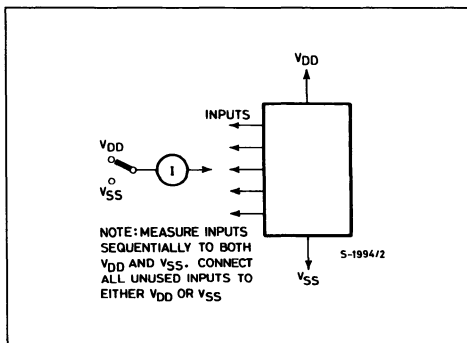
Quiescent Device Current.



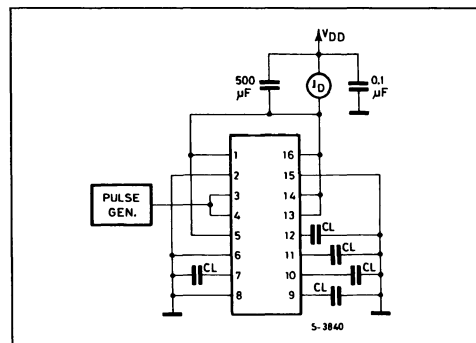
Input Voltage.



Input Leakage Current.

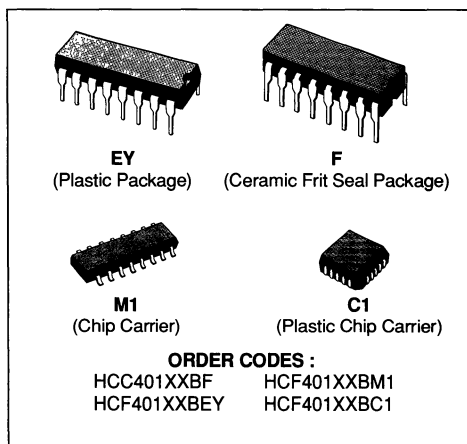


Dynamic Power Dissipation.



PRESETTABLE UP/DOWN COUNTERS (DUAL CLOCK WITH RESET) 40192B – BCD TYPE 40193B – BINARY TYPE

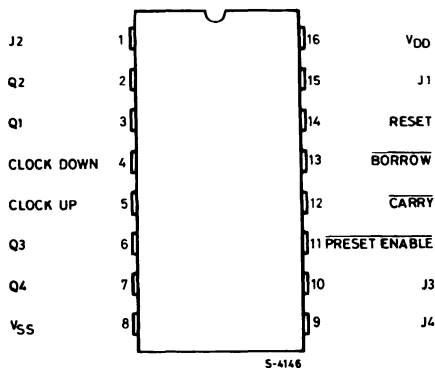
- INDIVIDUAL CLOCK LINES FOR COUNTING UP OR COUNTING DOWN
- SYNCHRONOUS HIGH-SPEED CARRY AND BORROW PROPAGATION DELAYS FOR CAS-CADING
- ASYNCHRONOUS RESET AND PRESET CAPABILITY
- MEDIUM-SPEED OPERATION - $f_{CL} = 8\text{MHz}$ (typ.) @ 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



DESCRIPTION

The **HCC40192B**, **HCC40193B**, (extended temperature range) and the **HCF40192B**, **HCF40193B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package. The **HCC/HCF40192B** Presettable BCD Up/Down Counter and the **HCC/HCF40193B** Presettable Binary Up/Down Counter each consist of 4 synchronously clocked, gated "D" type flip-flops connected as a counter. The inputs consist of 4 individual jam lines, a PRESET ENABLE control, individual CLOCK UP and CLOCK DOWN signals and a master RESET. Four buffered Q signal outputs as well as CARRY and BORROW outputs for multiple-stage counting schemes are provided. The counter is cleared so that all outputs are in a low state by a high on the RESET line. A RESET is accomplished asynchronously with the clock. Each output is individually programmable asynchronously with the clock to the level on the corresponding jam input when the PRESET ENABLE control is low. The counter counts up one count on the positive clock edge of the CLOCK UP signal provided the CLOCK DOWN line is high. The counter counts down one count on the positive clock edge of the CLOCK DOWN signal provided the CLOCK UP line

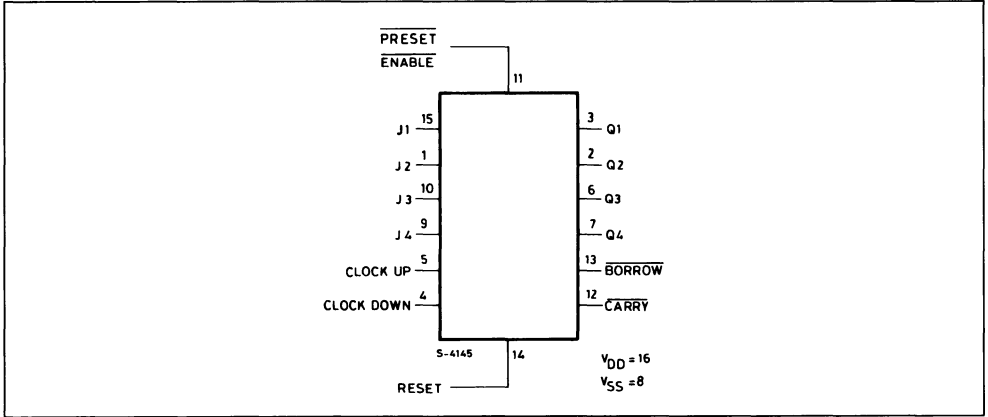
PIN CONNECTIONS



is high. The **CARRY** and **BORROW** signals are high when the counter is counting up or down. The **CARRY** signal goes low one-half clock cycle after the counter reaches its maximum count in the count-up mode. The **BORROW** signal goes low one-half clock cycle after the counter reaches its minimum

count in the count-down mode. Cascading of multiple packages is easily accomplished without the need for additional external circuitry by tying the **BORROW** and **CARRY** outputs to the **CLOCK DOWN** and **CLOCK UP** inputs, respectively, of the succeeding package.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

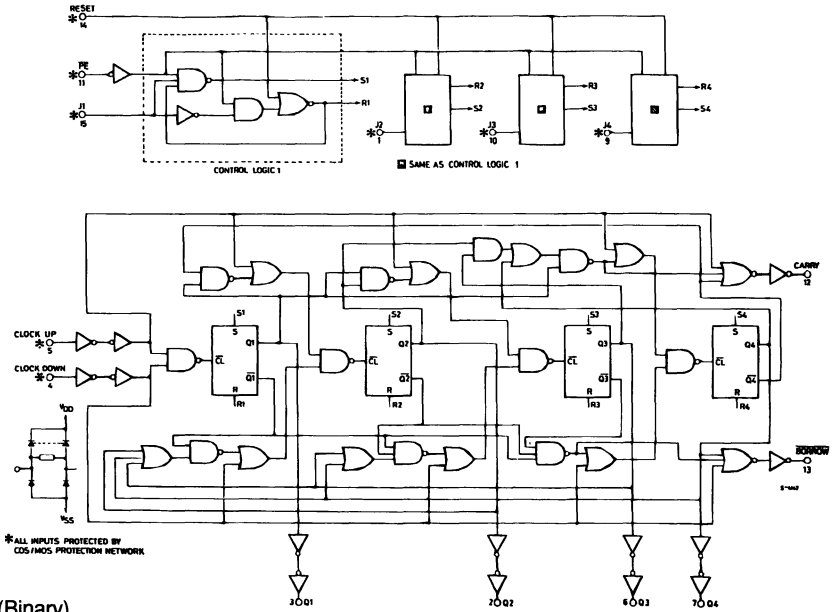
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

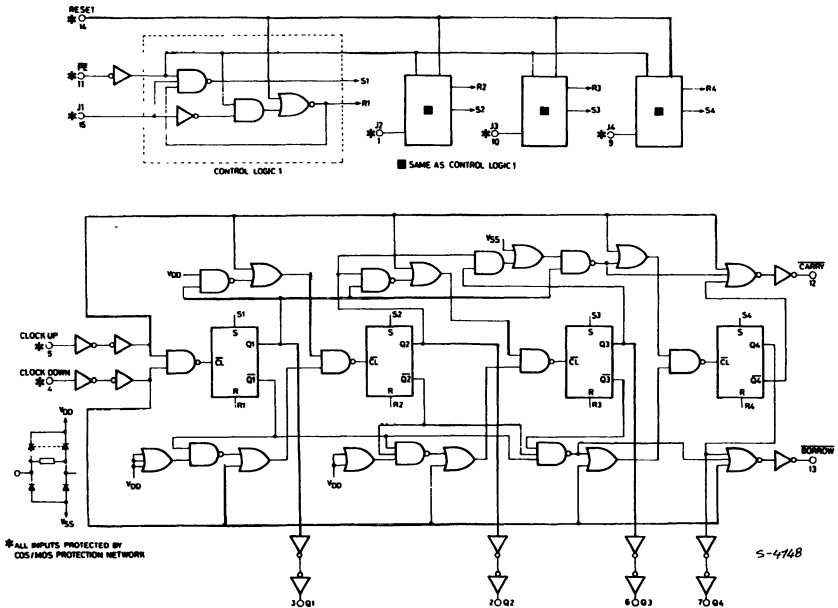
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAMS

40192B (BCD).

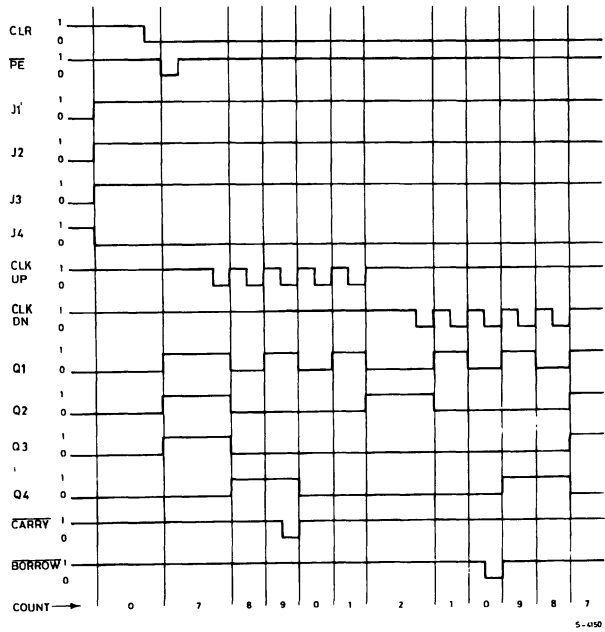


40193B (Binary).

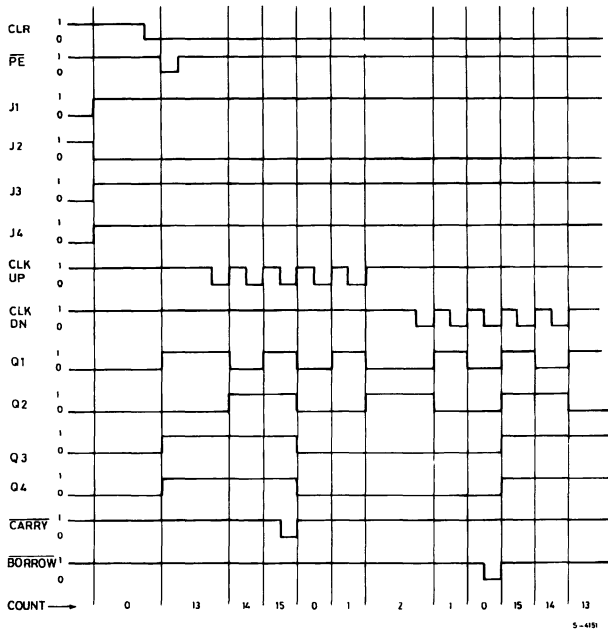


TIMING DIAGRAMS

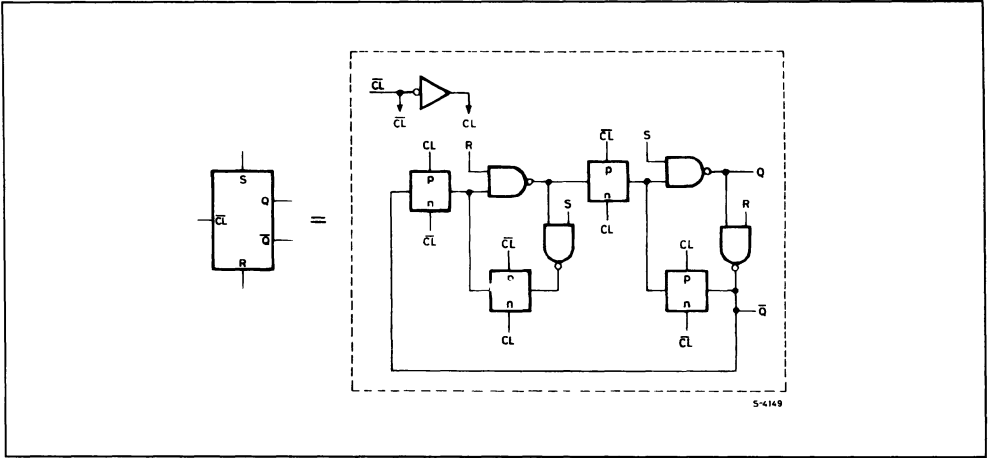
40192B (BCD).



40193B (Binary).



Internal Logic of Flip-flop.



TRUTH TABLE

Clock Up	Clock Down	Preset Enable	Reset	Action
	1	1	0	Count Up
	1	1	0	No Count
1		1	0	Count Down
1		1	0	No Count
X	X	0	0	Preset
X	X	X	1	Reset

1 = High Level 0 = Low Level X = Don't Care.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit		
		V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
						Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μ A
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	- 2		- 1.6	- 3.2		- 1.15	mA	
			0/ 5	4.6		5	- 0.64		- 0.51	- 1		- 0.36		
			0/10	9.5		10	- 1.6		- 1.3	- 2.6		- 0.9		
			0/15	13.5		15	- 4.2		- 3.4	- 6.8		- 2.4		
		HCF Types	0/ 5	2.5		5	- 1.53		- 1.36	- 3.2		- 1.1		
			0/ 5	4.6		5	- 0.52		- 0.44	- 1		- 0.36		
	0/10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9				
	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4				
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		\pm 0.1		\pm 10 ⁻⁵	\pm 0.1		\pm 1	μ A	
		HCF Types	0/15											15
C _I	Input Capacitance		Any Input						5	7.5			pF	

* T_{Low} = - 55°C for HCC device - 40°C for HCF device

* T_{High} = + 125°C for HCC device + 85°C for HCF device

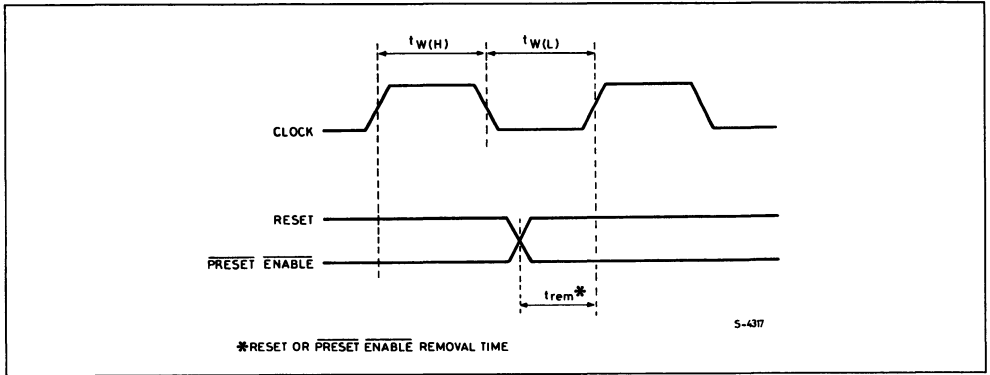
The Noise Margin for both "1" and "0" level is 1V min with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min with V_{DD} = 15V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

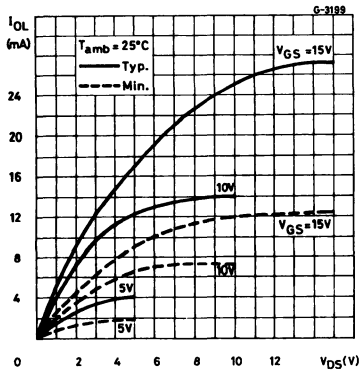
Symbol	Parameter	Test Conditions	Value				Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} , t_{PLH}	Propagation Delay Time Clock Up or Clock Down to Q Reset to Q		5		250	500	ns
			10		120	240	
			15		90	180	
	$\overline{\text{PE}}$ to Q		5		200	400	ns
			10		100	200	
			15		70	140	
	Clock Up to $\overline{\text{Carry}}$ Clock Down to Borrow		5		160	320	ns
			10		80	160	
			15		60	120	
	Reset or PR to Borrow or $\overline{\text{Carry}}$		5		300	600	ns
			10		150	300	
			15		110	220	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t_{rem}^*	Removal Time Reset or $\overline{\text{PE}}$		5	80	40		ns
			10	40	20		
			15	30	15		
t_w	Clock Input Pulse Width Reset		5	480	240		ns
			10	300	150		
			15	260	130		
	$\overline{\text{PE}}$		5		120	240	ns
			10		85	170	
			15		70	140	
	Clock		5		90	180	ns
			10		45	90	
			15		30	60	
t_r , t_f	Clock Input Rise or Fall Time		5			15	μs
			10			15	
			15			5	
f_{CL}	Maximum Clock Input Frequency		5	2	4		MHz
			10	5	8		
			15	5.5	11		

* The time required for Reset or Preset Enable control to be removed before clocking (see timing diagram).

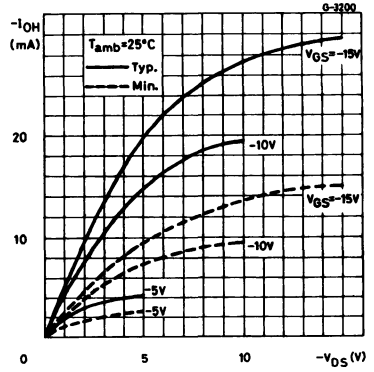
Timing Diagram Defining t_{rem} .



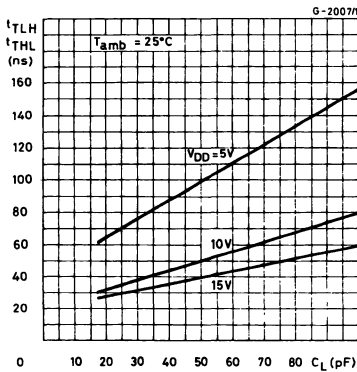
Output Low (sink) Current Characteristics.



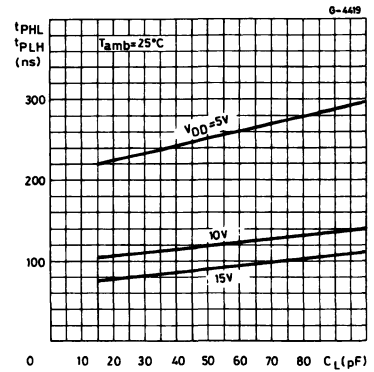
Output high (source) Current Characteristics.



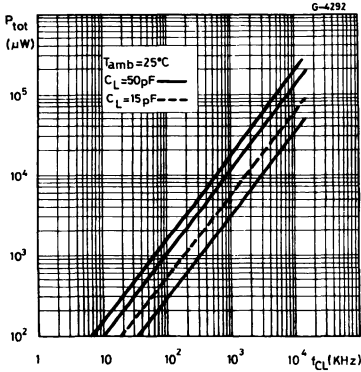
Typical Transition Time vs. Load Capacitance.



Typical Propagation Delay Time vs. Load Capacitance.

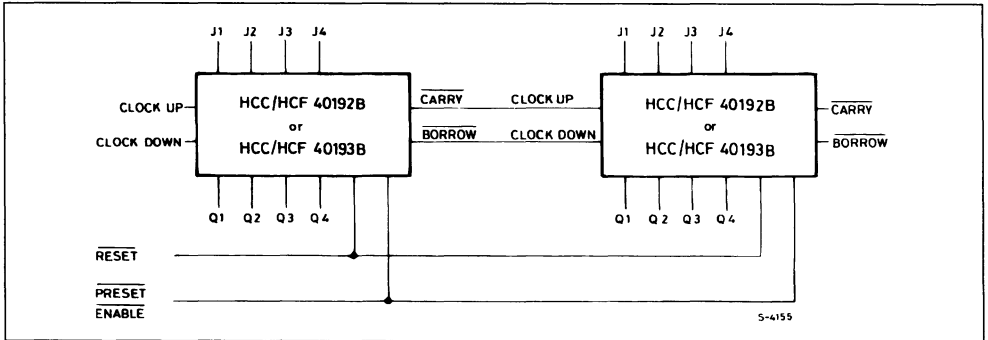


Typical Dynamic Power Dissipation.



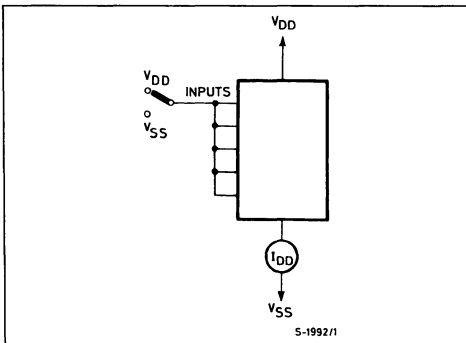
TYPICAL APPLICATION

CASCADED COUNTER PACKAGES

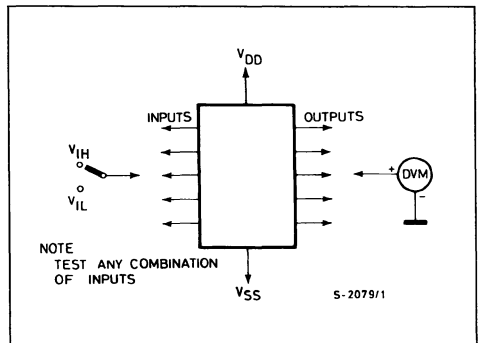


TEST CIRCUITS

Quiescent Device Current.

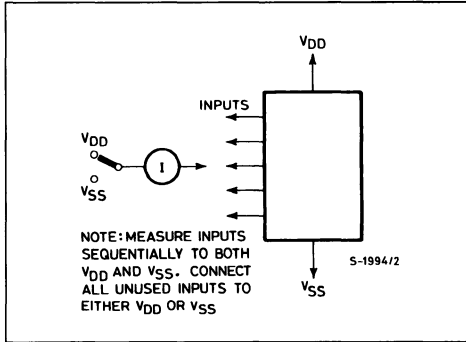


Input Voltage.

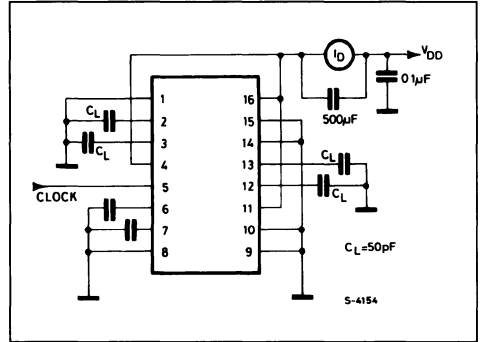


TEST CIRCUITS (continued)

Input Leakage Current.



Dynamic Power Dissipation.

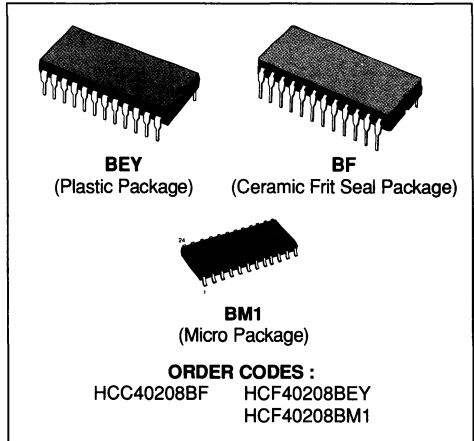


4 x 4 MULTIPOINT REGISTER

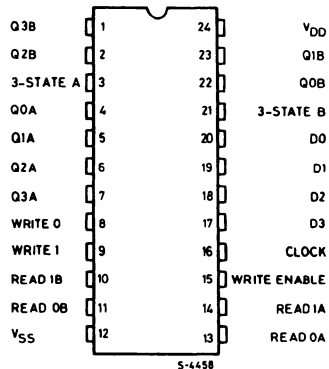
- FOUR 4-BIT REGISTERS
- ONE INPUT AND TWO OUTPUT BUSES
- UNLIMITED EXPANSION IN BIT AND WORD DIRECTIONS
- DATA LINES HAVE LATCHED INPUTS
- 3-STATE OUTPUTS
- SEPARATE CONTROL OF EACH BUS, ALLOWING SIMULTANEOUS INDEPENDENT READING OF ANY OF FOUR REGISTERS ON BUS A AND BUS B AND INDEPENDENT WRITING INTO ANY OF THE FOUR REGISTERS
- 40108B IS PIN-COMPATIBLE WITH INDUSTRY TYPE MC14580
- STANDARDIZED, SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

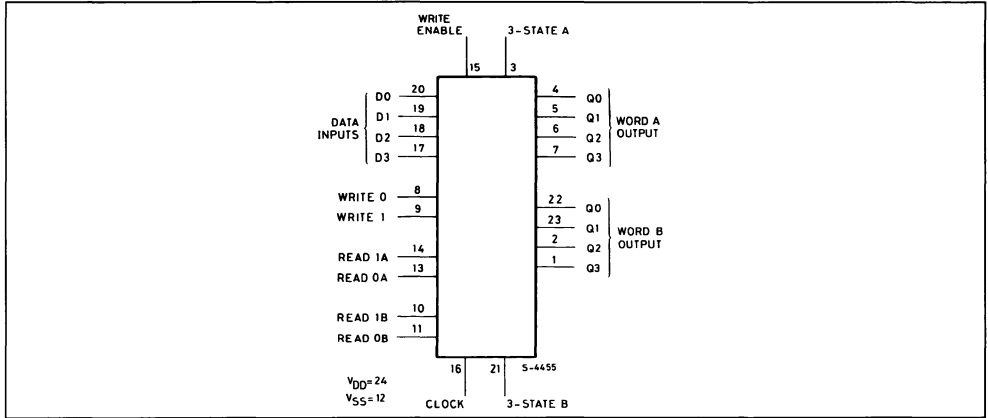
The HCC40208B (extended temperature range) and HCF40208B (intermediate temperature range) are monolithic integrated circuits, available in 24-lead dual in-line plastic or ceramic package and plastic micro package. The HCC/HCF40208B is a 4 x 4 multipoint register containing four 4-bit registers, write address decoder, two separate read address decoders, and two 3-state output buses. When the ENABLE input is low, the corresponding output bus is switched, independently of the clock to a high-impedance state. The high-impedance third state provides the outputs with the capability of being connected to the bus lines in a bus-organized system without the need for interface or pull-up components. When the WRITE ENABLE input is high, all data input lines are latched on the positive transition of the CLOCK and the data is entered into the word selected by the write address lines. When WRITE ENABLE is low, the CLOCK is inhibited and no new data is entered. In either case, the contents of any word may be accessed via the read address lines independent of the state of the CLOCK input.



PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

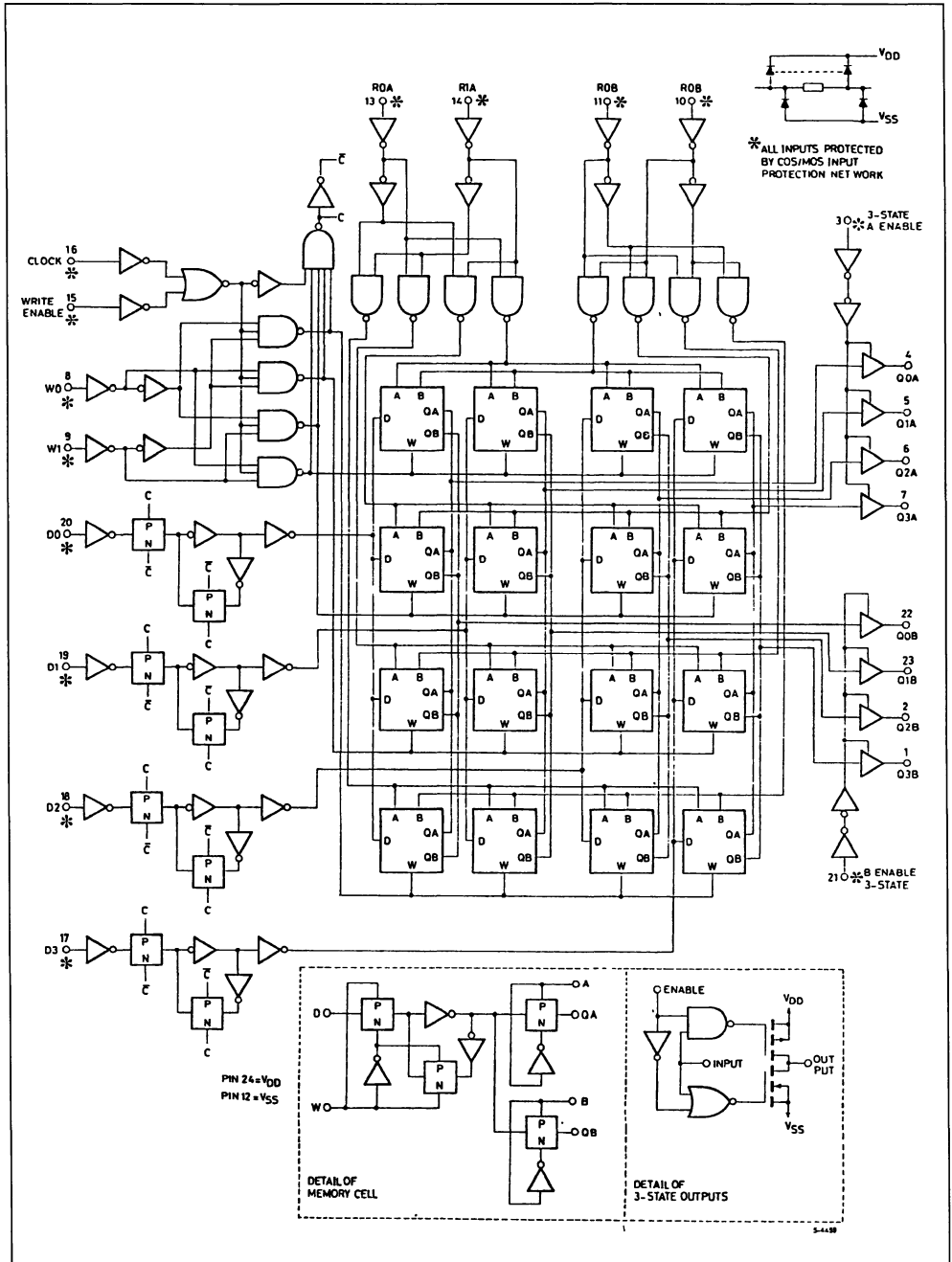
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. * All voltages are with respect to V_{SS} (GND)

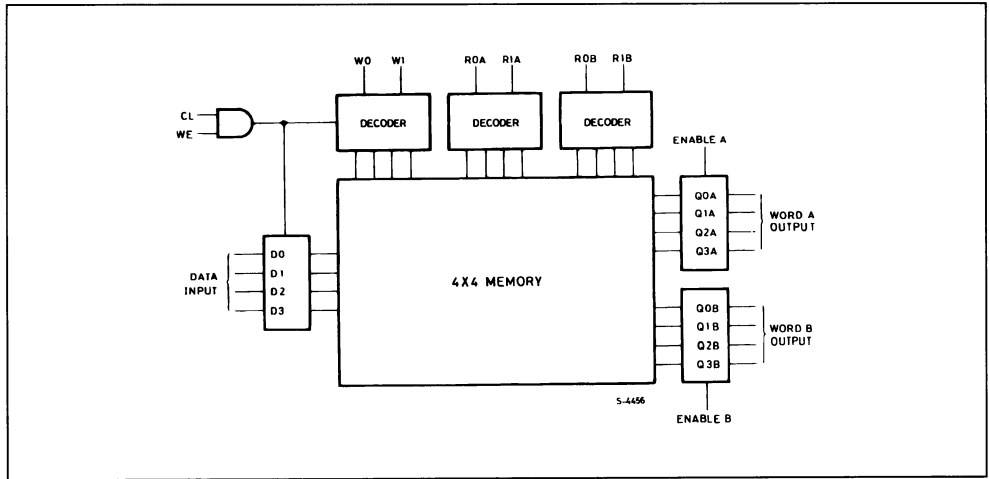
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

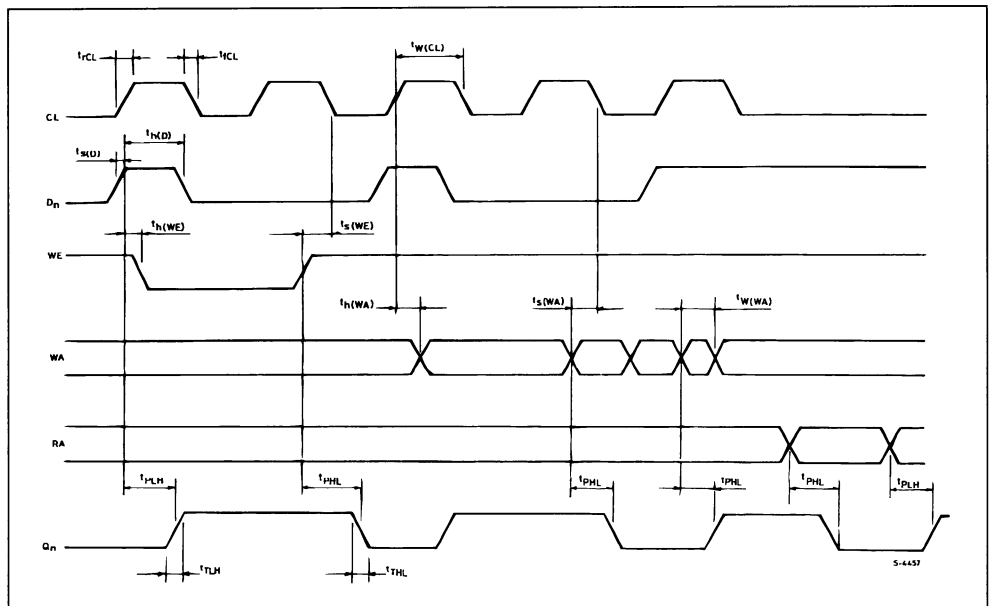
SCHEMATIC DIAGRAM



LOGIC DIAGRAM



TIMING DIAGRAM



TRUTH TABLE

Clock	Write Enable	Write 1	Write 0	Read 1A	Read 0A	Read 1B	Read 0B	Enable A	Enable B	D _n	Q _{nA}	Q _{nB}
	1	S1	S2	S1	S2	S1	S2	1	1	1	1	1
	1	S1	S2	S1	S2	S1	S2	1	1	0	0	0
X	X	X	X	X	X	X	X	0	0	X	Z	Z
	1	0	0	0	1	1	0	1	1	D _n to Word 0	Word 1 Out	Word 2 Out
	0	0	0	0	1	1	0	1	1	Word 0 Not Altered	Word 1 Out	Word 2 Out
X	X	X	X	1	0	0	1	1	1	X	Word 2 Out	Word 1 Out
	X	X	X	X	X	X	X	1	1	X	NC	NC

1 = HIGH LEVEL, 0 = LOW LEVEL, X = DON'T CARE, Z = HIGH IMPEDANCE.
S1 and S2 refer to input strates of either 1 or 0.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions.				Value						Unit
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C		T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.	
I _L	Quiescent Current	HCC Types	0/5			5		5		0.04	5	150	μA
			0/10			10		10		0.04	10	300	
			0/15			15		20		0.04	20	600	
			0/20			20		100		0.08	100	3000	
		HCF Types	0/5			5		20		0.04	20	150	
			0/10			10		40		0.04	40	300	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95	V	
		0/10		< 1	10	9.95		9.95			9.95		
		0/15		< 1	15	14.95		14.95			14.95		
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05	0.05	V	
		10/0		< 1	10		0.05			0.05	0.05		
		15/0		< 1	15		0.05			0.05	0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5	V	
			1/9	< 1	10	7		7			7		
			1.5/13.5	< 1	15	11		11			11		
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5	1.5	V	
			9/1	< 1	10		3			3	3		
			13.5/1.5	< 1	15		4			4	4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36	
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9	
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4	
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1	
			0/5	4.6		5	-0.52		-0.44	-1		-0.36	
	0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
	0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.

* T_{High} = +125°C for HCC device ; +85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

** Forced output disable.

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _{OL} (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15	Any Input		15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1		
I _{OH} , I _{OL} **	3-State Output Leakage Current	HCC Types	0/18	0/18		18		± 0.4	$\pm 10^{-4}$	± 0.4		± 12	μ A	
		HCF Types	0/15	0/15		15		± 1.0	$\pm 10^{-4}$	± 1.0		± 7.5		
C _I	Input Capacitance	Any Input						5	7.5			pF		

* T_{Low} = -55°C for HCC device ; -40°C for HCF device.

* T_{High} = +125°C for HCC device ; +85°C for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

** Forced output disable.

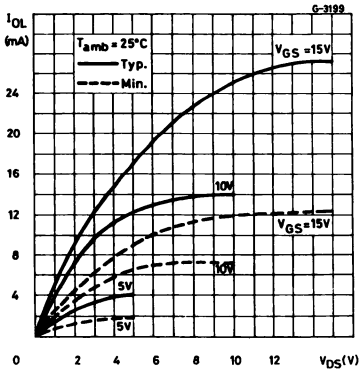
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200k Ω , typical temperature coefficient for all V_{DD} values is 0.3%/°C, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _{PHL} , t _{PLH}	Propagation Delay Time : Clock to Write Enable to Q		5		360	720	ns
			10		140	280	
			15		100	200	
	Read or Write Address to Q		5		300	600	ns
			10		120	240	
			15		85	170	
t _{PZH} , t _{PHZ}	3-state Disable Delay Time		5		100	200	ns
			10		50	100	
			15		40	80	
t _{PZL} , t _{PLZ}	3-State Disable Delay time		5		130	260	ns
			10		60	120	
			15		50	100	
t _{THL} , t _{TLH}	Output Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	
t _{setup}	Setup Time Data to Clock t _{s(D)}		5	0	-95		ns
			10	0	-35		
			15	0	-20		
	Write Enable to $\overline{\text{Clock}}$ t _{s(WE)}		5	250	125		ns
			10	100	50		
			15	70	35		
Write Address to $\overline{\text{Clock}}$ t _{s(WA)}		5	250	125		ns	
		10	100	50			
		15	70	35			

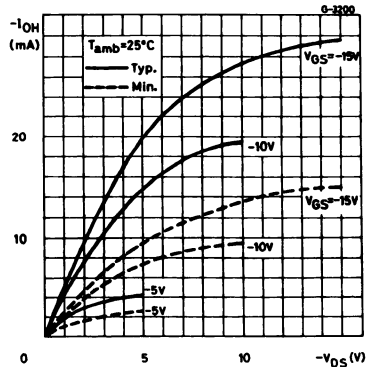
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions		Value			Unit
			V _{DD} (V)	Min.	Typ.	Max.	
t _r , t _f	Clock Rise and Fall Time		5			15	μs
			10			5	
			15			5	
t _{hold}	Hold Time Data to Clock t _{h(D)}		5	220	110		ns
			10	100	50		
			15	80	40		
	Write Enable to Clock t _{h(WE)}		5	270	135		ns
			10	130	65		
			15	80	40		
Write Address to Clock t _{s(WA)}		5	330	165			
		10	140	70			
		15	90	45			
t _w	Clock Pulse Width Clock or Write Enable t _{w(CL)}		5	350	175		ns
			10	130	65		
			15	90	45		
	Write Address t _{w(WA)}		5	300	150		ns
			10	150	75		
			15	90	45		
f _{CL}	Maximum Clock Input Frequency		5	1.5	3		MHz
			10	3.5	7		
			15	4.5	9		

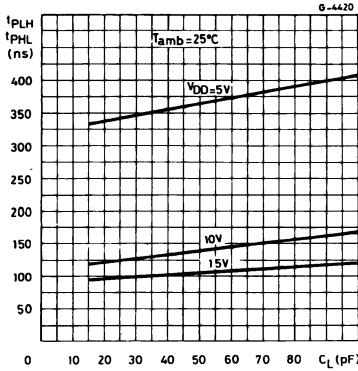
Output Low (sink) Current Characteristics.



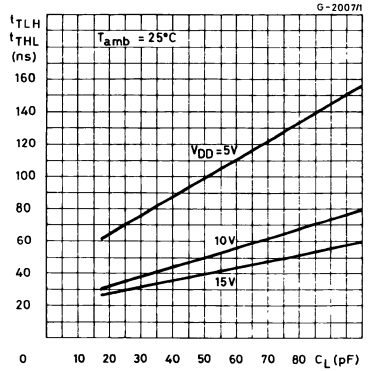
Output High (source) Current Characteristics.



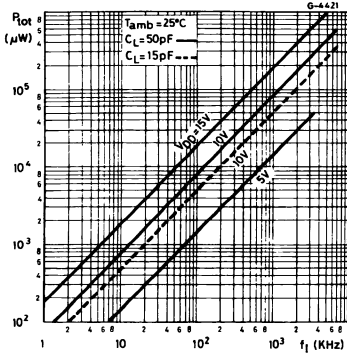
Typical Propagation Delay Time vs. Load Capacitance (CL or WE to Q).



Typical Transition Time vs. Load Capacitance.

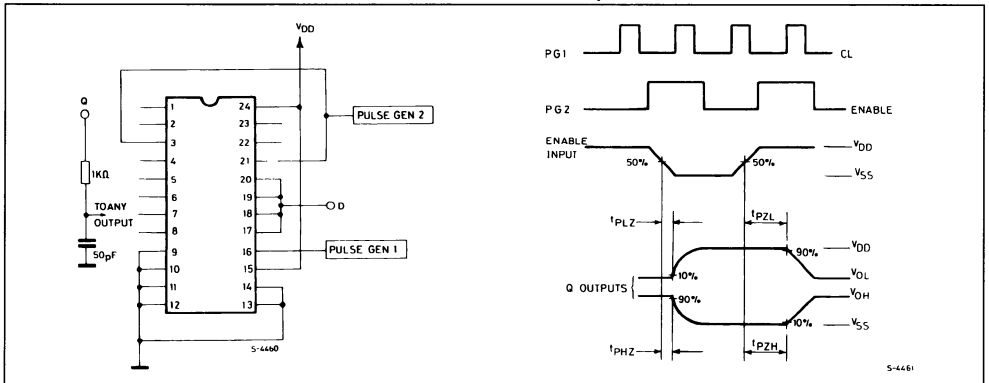


Typical Dynamic Power Dissipation vs. Input Frequency.

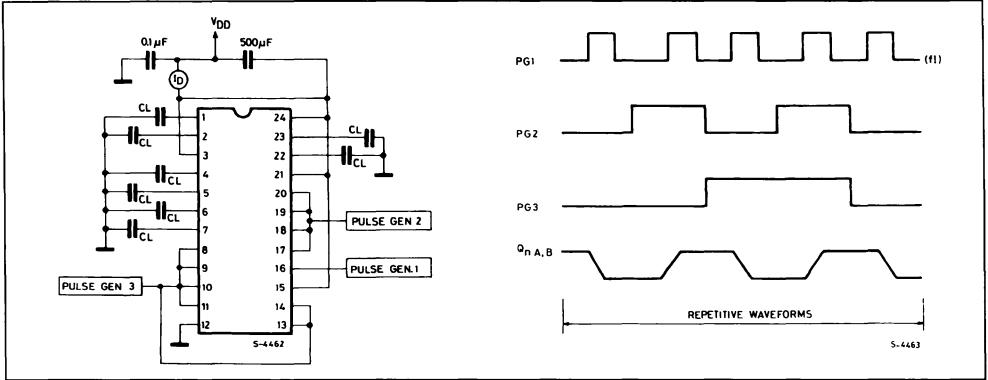


TEST CIRCUITS

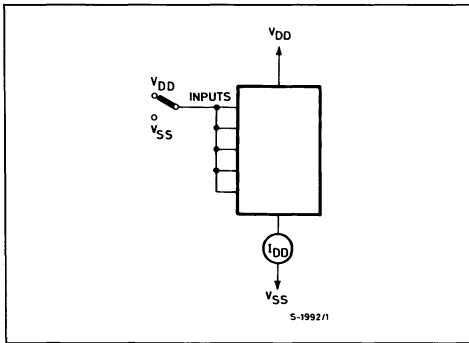
Output-enable-delay-times and Waveforms.



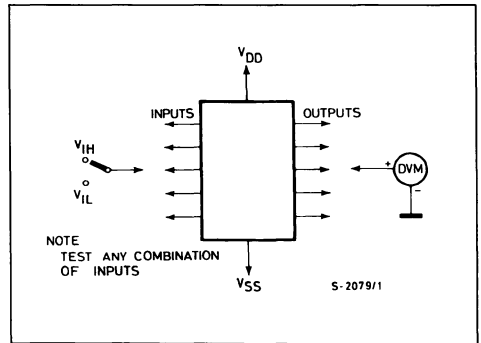
Power-dissipation and Waveforms.



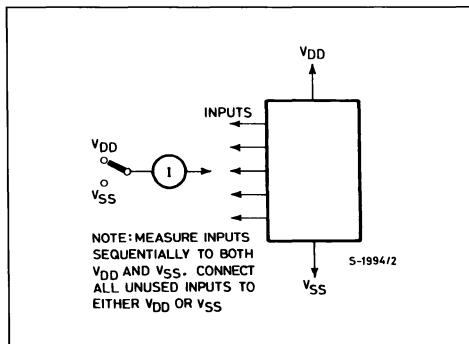
Quiescent Device Current.



Input Voltage.

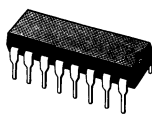


Input Current.

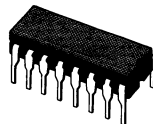


QUAD 2-LINE-TO-1-LINE DATA SELECTOR/MULTIPLEXER

- 3-STATE OUTPUTS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N° 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)

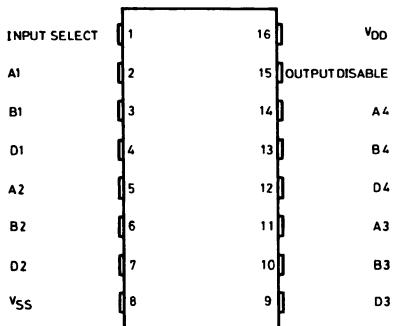


C1
(Plastic Chip Carrier)

ORDER CODES :

HCC40257BF HCF40257BM1
 HCF40257BEY HCF40257BC1

PIN CONNECTIONS



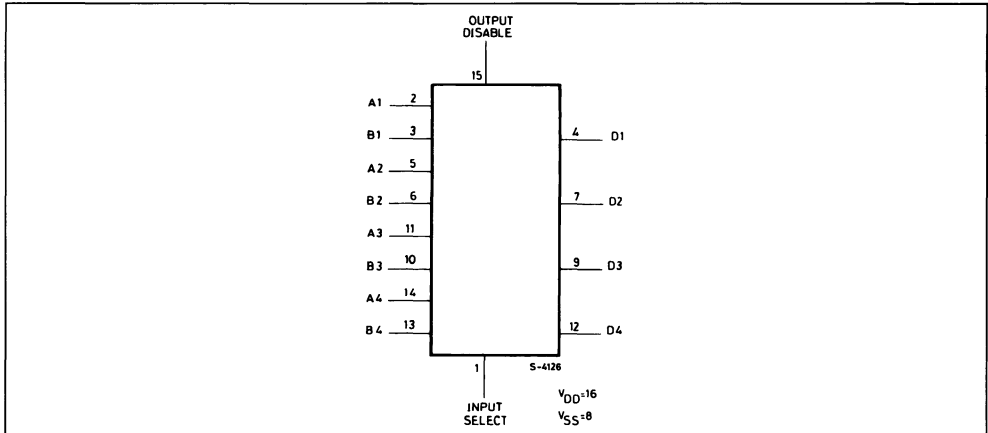
S-4128

DESCRIPTION

The **HCC40257B** (extended temperature range) and **HCF40257B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micro package.

The **HCC/HCF40257B** is a Data Selector/Multiplexer featuring three-state outputs which can interface directly with and drive data lines of bus-oriented systems.

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

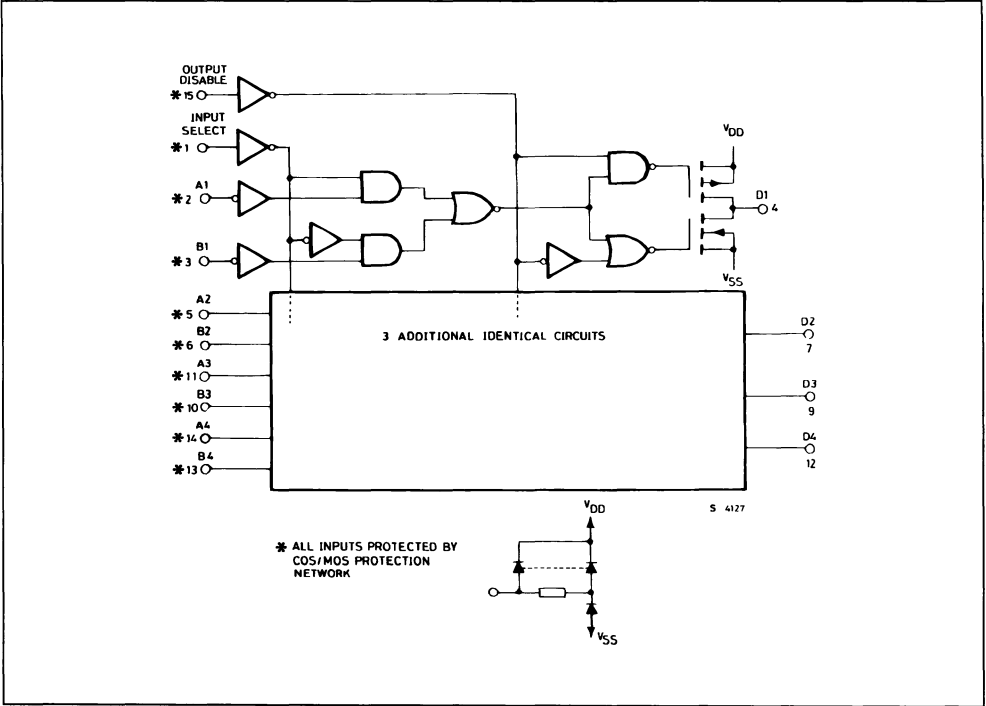
Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20	V
		- 0.5 to + 18	V
V _i	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _i	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package-temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
 * All voltages are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V _i	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125	°C
		- 40 to + 85	°C

LOGIC DIAGRAM



TRUTH TABLE

Inputs				Output
3-State Output Disable	Select	A	B	D
1	X	X	X	Z
0	0	0	X	0
0	0	1	X	1
0	1	X	0	0
0	1	X	1	1

X = Don't Care
 Logic 1 = High
 Logic 0 = Low
 Z = High impedance.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit		
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5			1		0.02	1		30	μ A
			0/10			10			2		0.02	2		60	
			0/15			15			4		0.02	4		120	
		0/20			20			20		0.04	20		600		
		HCF Types	0/5			5			4		0.02	4		30	
			0/10			10			8		0.02	8		60	
0/15				15			16		0.02	16		120			
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95			V	
		0/10		< 1	10	9.95		9.95			9.95				
		0/15		< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/10		< 1	5		0.05			0.05		0.05		V	
		10/0		< 1	10		0.05			0.05		0.05			
		15/0		< 1	15		0.05			0.05		0.05			
V _{IH}	Input High Voltage	0/5	0.5/4.5	< 1	5	3.5		3.5			3.5			V	
		0/10	1/9	< 1	10	7		7			7				
		0/15	1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage	0/5	4.5/0.5	< 1	5		1.5			1.5		1.5		V	
		0/10	9/1	< 1	10		3			3		3			
		0/15	13.5/1.5	< 1	15		4			4		4			
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36			
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9			
		0/15	13.5		15	-4.2		-3.4	-6.8		-2.4				
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52		-0.44	-1		-0.36			
0/10	9.5			10	-1.3		-1.1	-2.6		-0.9					
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9			
			0/15	1.5		15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36			
			0/10	0.5		10	1.3		1.1	2.6		0.9			
			0/15	1.5		15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1	$\pm 10^{-5}$	± 0.1		± 1	μ A		
		HCF Types	0/15	Any Input		15		± 0.3	$\pm 10^{-5}$	± 0.3		± 1			
I _{OH} , I _{OL} **	3-State Output Leakage Current	HCC Types	0/18	0/18		18		± 0.4	$\pm 10^{-4}$	± 0.4		± 12	μ A		
		HCF Types	0/18	0/18		18		± 1.0	$\pm 10^{-4}$	± 1.0		7.5			
C _I	Input Capacitance	Any Input						5	7.5			pF			

* T_{Low} = - 55°C for HCC device . - 40°C for HCF device.

* T_{High} = + 125°C for HCC device ; + 85°C for HCF device.

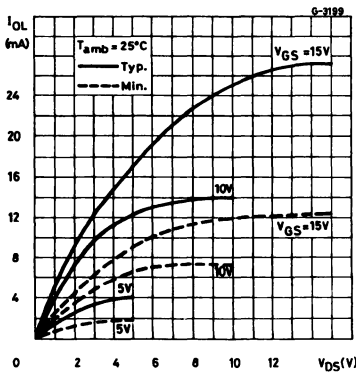
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V min. with V_{DD} = 15V.

** Forced output disable.

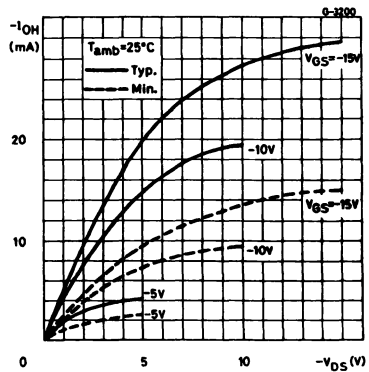
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall time = 20ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time Data Input to Output		5		150	300	ns
			10		70	140	
			15		50	100	
	Select to Output		5		190	380	ns
			10		85	170	
			15		65	130	
	Output Disable to Output		5		95	190	ns
			10		50	100	
			15		40	80	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

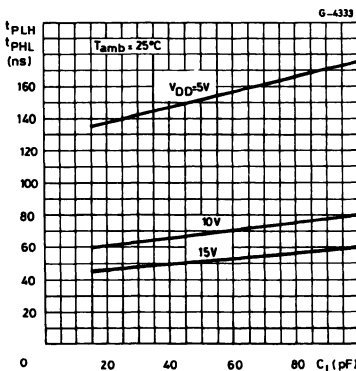
Output Low (sink) Current Characteristics.



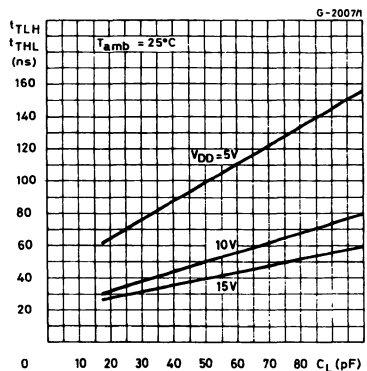
Output High (source) Current Characteristics.



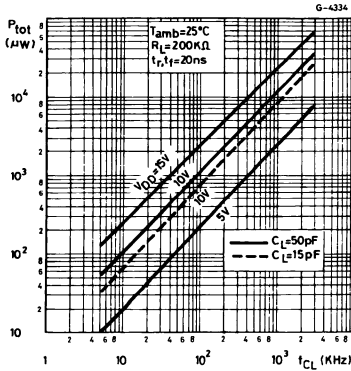
Typical Propagation Delay Time vs. Load Capacitance (Data Input to Output).



Typical Transition Time vs. Load Capacitance.

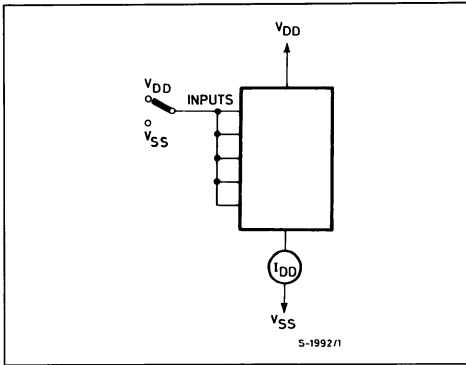


Typical Dynamic Power Dissipation vs. Input Frequency (one input to one output).

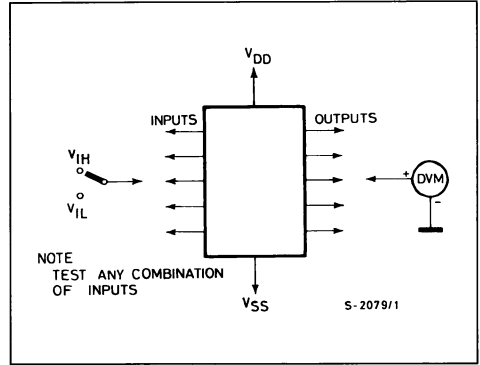


TEST CIRCUITS

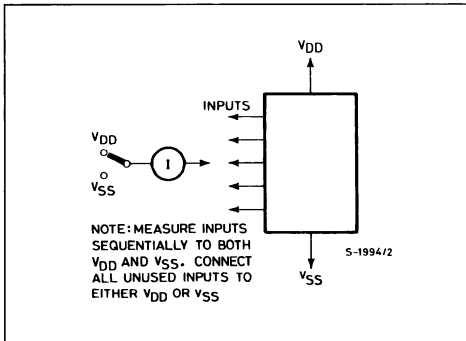
Quiescent Device Current.



Input Voltage.



Input Leakage Current.



4 X 4 CROSSPOINT SWITCH WITH CONTROL MEMORY

- LOW ON RESISTANCE – 75 Ω TYP. AT $V_{DD} = 12\text{ V}$
- "BUILT-IN" CONTROL LATCHES
- LARGE ANALOG SIGNAL CAPABILITY $\pm V_{DD}/2$
- TRANSMITS SIGNALS UP TO 10 MHz
- MATCHED SWITCH CHARACTERISTICS
 $\Delta R_{ON} = 18\ \Omega$ TYP. AT $V_{DD} - V_{SS} = 12\text{ V}$.
- HIGH LINEARITY : – 0.5 % DISTORTION (typ.)
AT $f = 1\text{ KHz}$, $V_{IN} = 5\text{ V}$ PEAK TO PEAK, $V_{DD} - V_{SS} = 10\text{ V}$, $R_L = 10\text{ K}\Omega$
- STANDARD COS/MOS NOISE IMMUNITY
- 100 % TESTED FOR QUIESCENT CURRENT

DESCRIPTION

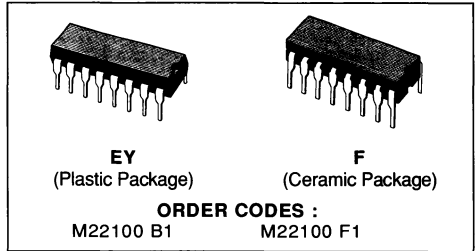
The M22100 combines a 4 x 4 array of crosspoints (transmission gates) with a 4-line-to-16-line decoder and 16 latch circuits. Any one of the sixteen transmission gates (crosspoints) can be selected by applying the appropriate four line address. The selected transmission gate can be turned on or off by applying a logical one or zero, respectively, to the data input and strobing the strobe input to a logical one. Any number of the transmission gates can be ON simultaneously.

When the required operating power is applied to the 22100, the states of the 16 switches are indeterminate.

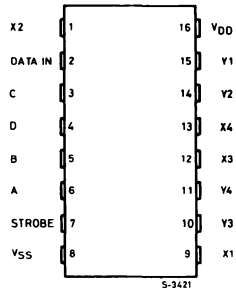
Therefore, all switches must be turned off by putting the strobe high and data-in-low, and then address-

sing all switches in succession.

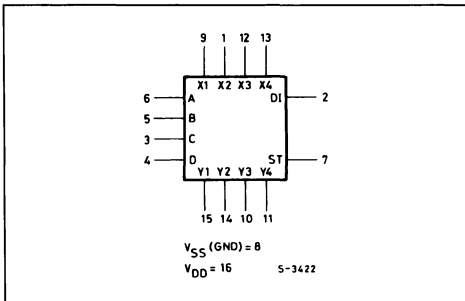
The device is available in 16 lead dual in-line plastic or ceramic package.



PIN CONNECTIONS



FUNCTIONAL DIAGRAM



TRUTH TABLE

Address				Select	Address				Select		
A	B	C	D		A	B	C	D			
0	0	0	0	X1	Y1	0	0	1	X1	Y3	
1	0	0	0	X2	Y1	1	0	0	1	X2	Y3
0	1	0	0	X3	Y1	0	1	0	1	X3	Y3
1	1	0	0	X4	Y1	1	1	0	1	X4	Y3
0	0	1	0	X1	Y2	0	0	1	1	X1	Y4
1	0	1	0	X2	Y2	1	0	1	1	X2	Y4
0	1	1	0	X3	Y2	0	1	1	1	X3	Y4
1	1	1	0	X4	Y2	1	1	1	1	X4	Y4

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: Ceramic Types Plastic Types	-0.5 to +20	V
		-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package Temperature Range	200	mW
		100	mW
T _{op}	Operating Temperature: Ceramic Types Plastic Types	-55 to +125	°C
		-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

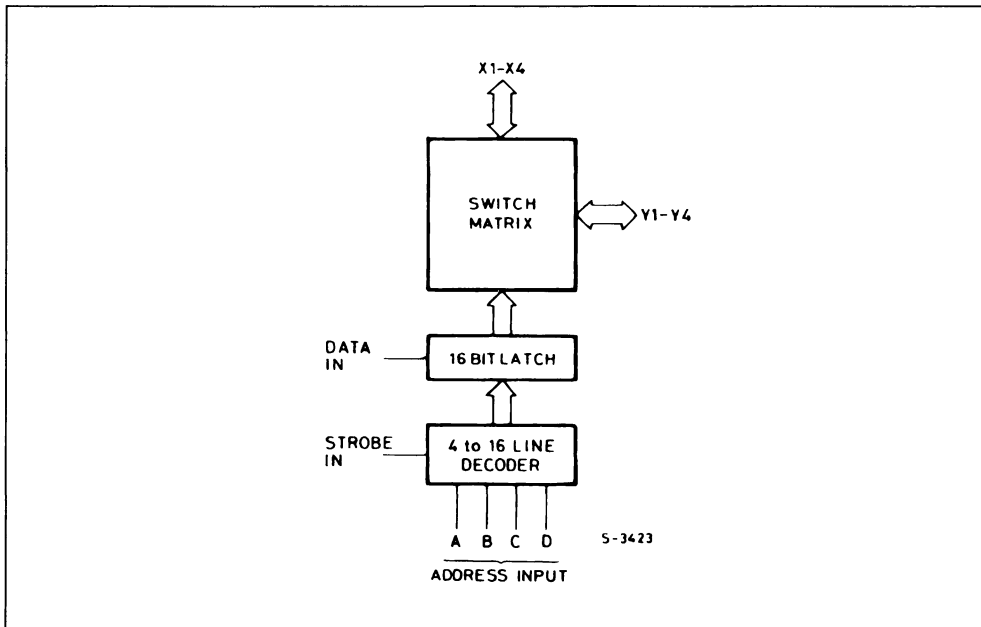
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: Ceramic Types Plastic Types	3 to 18	V
		3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: Ceramic Types Plastic Types	-55 to +125	°C
		-40 to +85	°C

LOGIC DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
			V _I (V)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *			
					Min.	Max.	Min.	Typ.	Max.	Min.	Max.		
CROSSPOINT													
I _L	Quiescent Supply Current	F1		5				0.04	5		150	μA	
				10				0.04	10		300		
				15				0.04	20		600		
				20				0.08	100		3000		
		B1		5				0.04	20		150		
				10				0.04	40		300		
				15				0.04	80		600		
R _{ON}	On Resistance	F1	Any Switch	5		450		225	1250		1625	Ω	
				10		135		85	180		230		
				12		100		75	135		175		
				15		70		65	95		125		
		B1		V _{IS} = 0 to V _{DD}	5		1000		225	1250			1440
					10		145		85	180			205
					12		110		75	135			155
					15		75		65	95			110
ΔON	Resistance ΔR _{ON} (Between any two channels)			5				35			Ω		
				10				20					
				12				18					
				15				15					
OFF Channel Leakage Current	F1	All Switch OFF	0/18	18		±0.1		±10 ⁻³	±0.1*		±1	μA	
				B1	0/15	15		±0.3		±10 ⁻³	±0.3		
CONTROL													
V _{IL}	Input Low Voltage	OFF Switch I _L < 0.2 μA		5		1.5			1.5		1.5	V	
				10		3			3		3		
				15		4			4		4		
V _{IH}	Input High Voltage	ON Switch see R _{ON} Characteristics		5	3.5		3.5			3.5		V	
				10	7		7			7			
				15	11		11			11			
I _I	Input Current	F1	Any Control Input	0/18	18		±0.1		±10 ⁻⁵	±0.1*		±1	μA
		B1		0/15	15		±0.3		±10 ⁻⁵	±0.3		±1	
C _I	Input Capacitance	Any Input						5	7.5			pF	

* Determined by minimum feasible leakage measurement for automatic testing

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions				Value			Unit
		f_i (KHz)	R_L (KW)	$V_{IS} \cdot$ (V)	V_{DD} (V)	Min.	Typ.	Max.	
CROSSPOINT									
t_{PHL} t_{PLH}	Propagation Delay Time Address or Strobe Inputs to Output		10	5 10 15	5 10 15		30 15 10	60 30 20	ns
	Frequency Response (Any Switch ON)	1	1	5	10		40		MHz
		Sine Wave Input $20 \text{ Log} \frac{V_{OS}}{V_{IS}} = -3 \text{ dB}$							
	Sine Wave Distortion	1	1	5	10		0.5		%
	Feedthrough (All Switches OFF)	1.6	1	5	10		80		dB
		Sine Wave Input							
	Frequency for Signal Crosstalk Attenuation of 40 dB		1	10	10		1.5		MHz
		Sine Wave Input							
	Frequency for Signal Crosstalk Attenuation of 110 dB		1	10	10		0.1		KHz
		Sine Wave Input							
C	Capacitance Xn to Ground Yn to Ground Feedthrough				5-15		18 30 0.4		pF
CONTROLS									
t_{PHZ}	Propagation Delay Time Strobe to Output (Switch Turn-ON to High Level)	$R_L = 1\text{ K}\Omega$ $C_L = 50\text{ pF}$ $t_r, t_f = 20\text{ ns}$	See Figure 1	5		500	1000	ns	
				10		230	460		
				15		145	290		
t_{PZH}	Propagation Delay Time Data-In to Output (Switch Turn-ON to High Level)		See Figure 2	5		500	1000	ns	
				10		220	440		
				15		135	270		
t_{PZH}	Propagation Delay Time Address to Output (Switch Turn-ON to High Level)		See Figure 3	5		480	960	ns	
				10		225	450		
				15		150	300		
t_{PHZ}	Propagation Delay Time Strobe to Output (Switch Turn-OFF)		See Figure 1	5		450	900	ns	
				10		200	400		
				15		165	330		
t_{PZL}	Propagation Delay Time Data-In to Output (Switch Turn-ON to Low Level)		See Figure 2	5		500	1000	ns	
				10		220	440		
				15		135	270		
t_{PHZ}	Propagation Delay Time Address to Output (Switch Turn-OFF)	See Figure 3	5		425	850	ns		
			10		190	380			
			15		145	290			
t_{setup}	Setup Time Data-In to Strobe, Address		5		200	400	ns		
			10		80	160			
			15		50	100			

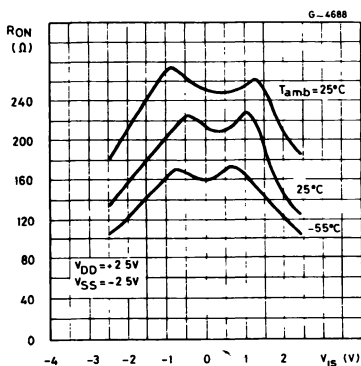
• Peak to peak voltage symmetrical about $V_{DD}/2$

DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

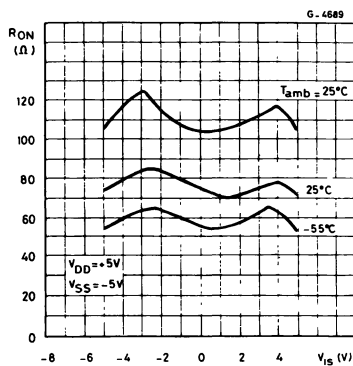
Symbol	Parameter	Test Conditions				Value			Unit		
		f_i (KHz)	R_L (KW)	V_{IS} (V)	V_{DD} (V)	Min.	Typ.	Max.			
CONTROLS (continued)											
t_{hold}	Hold Time Data-In to Strobe, Address	$R_L = 1\text{ K}\Omega$ $C_L = 50\text{ pF}$				5		180		ns	
						10		110			
						15		35			
$f\phi$	Switching Frequency	$t_r, t_f = 20\text{ ns}$				5	0.6	1.2		MHz	
						10	1.6	3.2			
						15	2.5	5			
t_w	Strobe Pulse Width					5		300	600	ns	
						10		120	240		
						15		90	180		
	Control Crosstalk Data-In, Address, or Strobe to Output				10	10	10		75		mV (peak)

• Peak to peak voltage symmetrical about $V_{DD}/2$

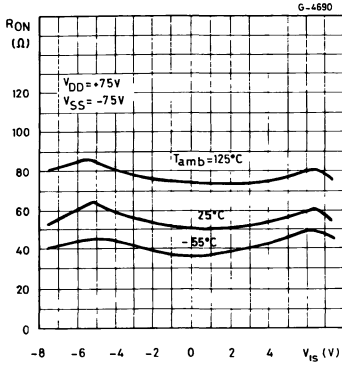
Typical ON Resistance vs. Input Signal Voltage at $V_{DD} = -V_{SS} = 2.5\text{ V}$.



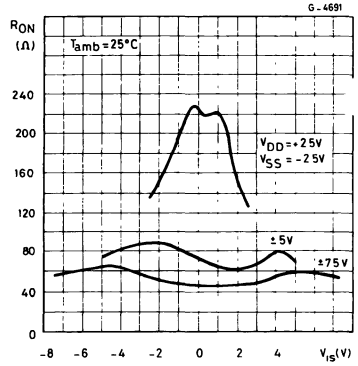
Typical ON Resistance vs. Input Signal Voltage at $V_{DD} = -V_{SS} = 5\text{ V}$.



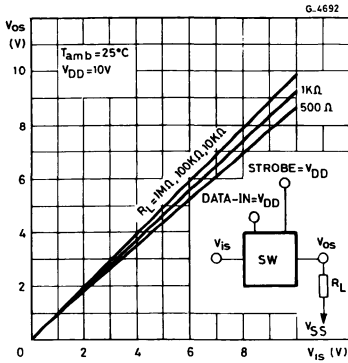
Typical ON Resistance vs. Input Signal Voltage at $V_{DD} = -V_{SS} = 7.5\text{ V}$.



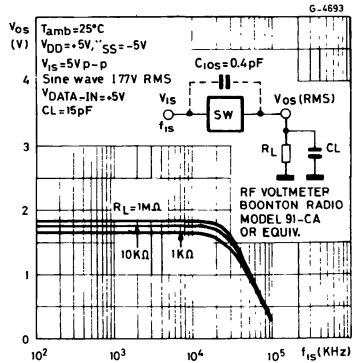
Typical ON Resistance vs.. Input Signal Voltage at $T_{amb} = 25^\circ\text{C}$.



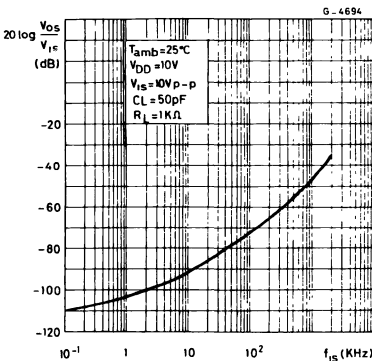
Typical Switch ON Transfer Characteristics (1 of 16 switches).



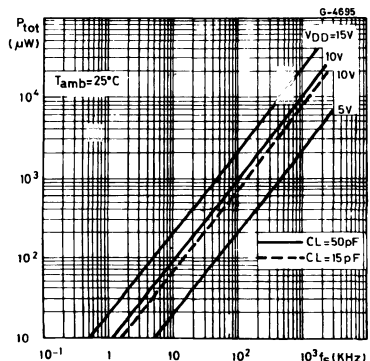
Typical Switch ON Frequency Response Characteristics.



Typical Crosstalk Between switches vs. Signal Frequency.

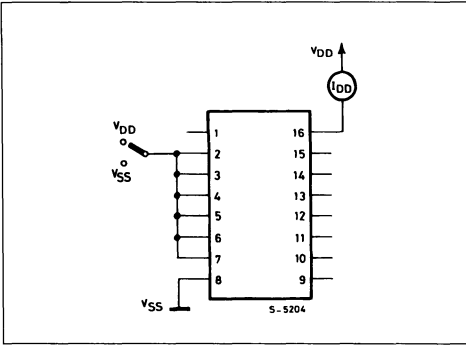


Typical Dynamic Power Dissipation vs. Switching Frequency..

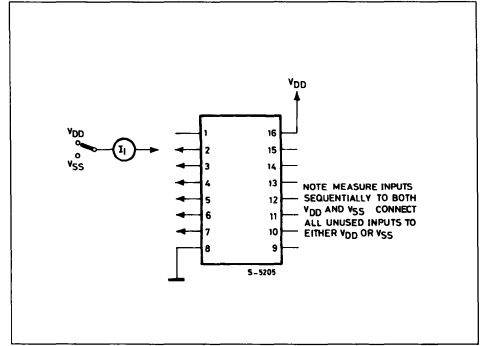


TEST CIRCUITS

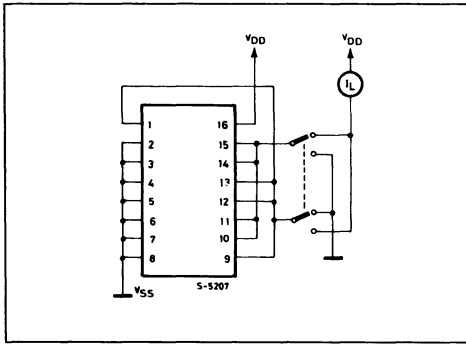
Quiescent Current.



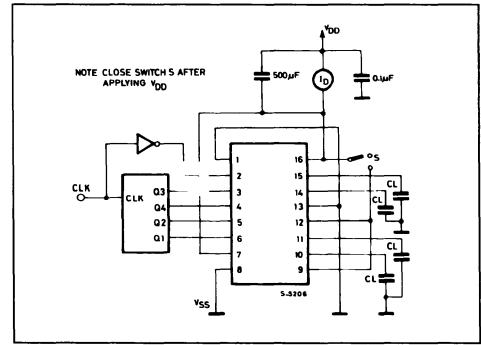
Input Current.



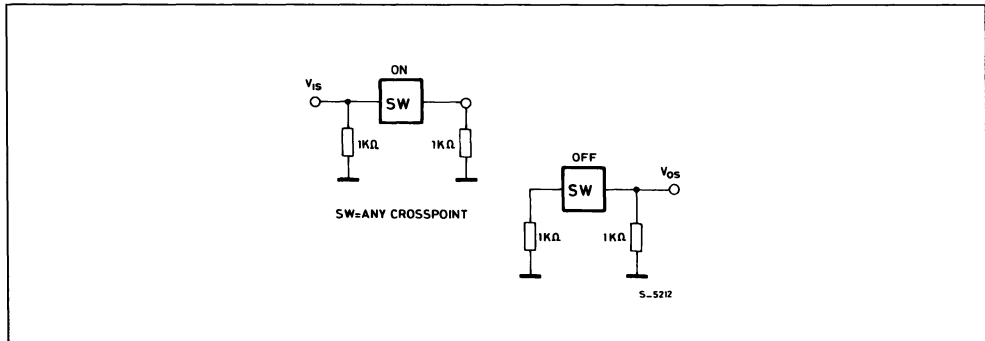
Off Switch Input or Output Leakage Current.



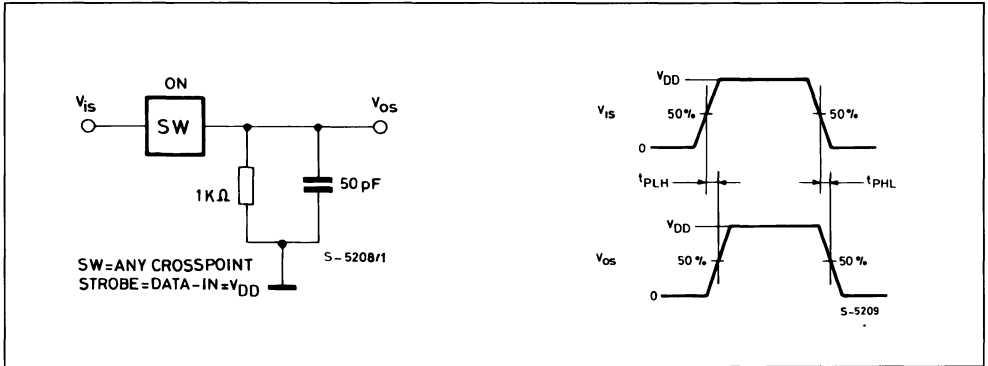
Dynamic Power Dissipation.



Crostalk Between Switch Circuits in the Same Package.



Propagation Delay Time and Waveforms (signal input to signal output, switch ON).



Waveforms for Crosstalk (control input to signal output).

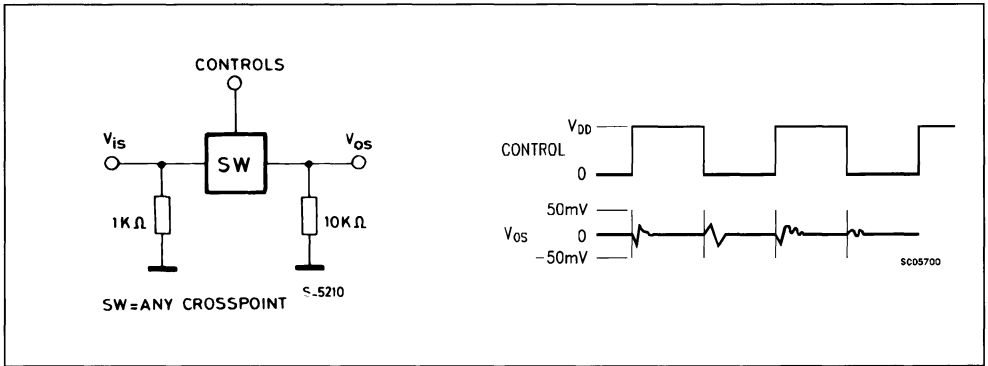


Figure 1 : Propagation Delay Time and Waveforms (strobe to signal output, switch Turn-ON or Turn-OFF).

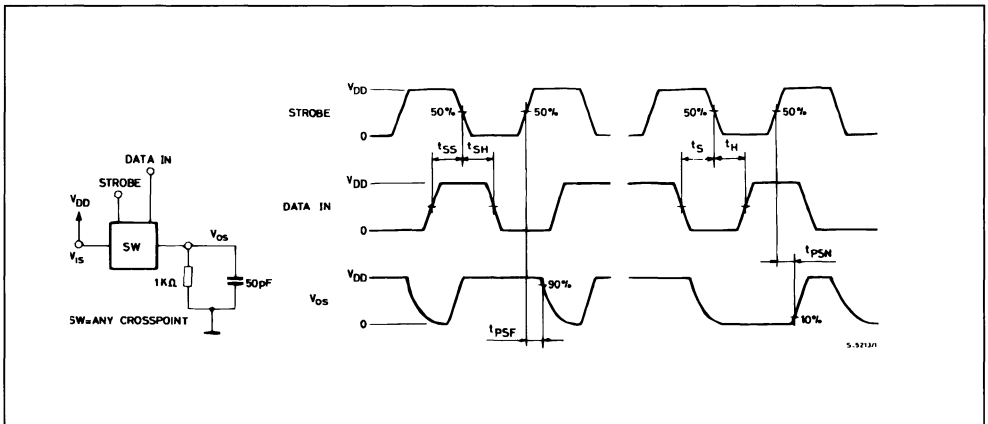


Figure 2 : Propagation Delay Time and Waveforms (data-in to signal output, switch Turn-ON to high or low level).

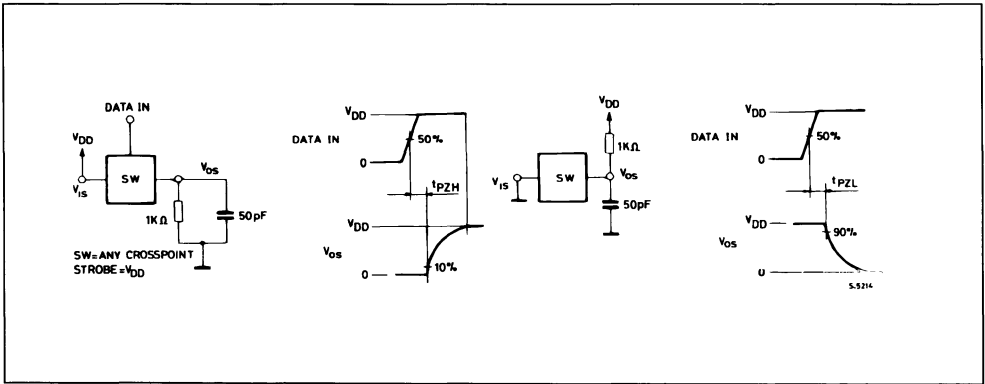
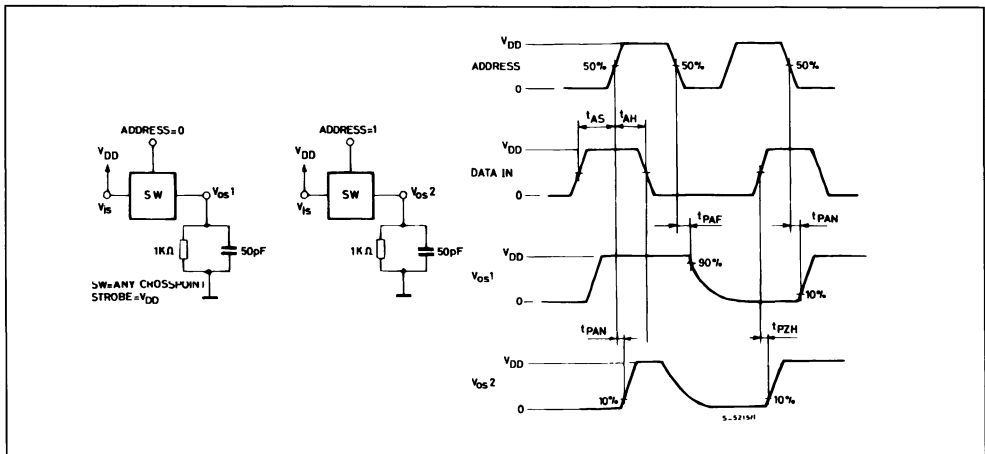


Figure 3 : Propagation Delay Time and Waveforms (address to signal output switch Turn-ON or Turn-OFF).



4 X 4 X 2 CROSSPOINT SWITCHES WITH CONTROL MEMORY

- LOW ON RESISTANCE – 75 Ω TYP AT $V_{DD} = 12\text{ V}$
- "BUILT-IN" LATCHED INPUTS
- LARGE ANALOG SIGNAL CAPACITY $\pm V_{DD}/2$
- 10 MHz SWITCH BANDWIDTH
- MATCHED SWITCH CHARACTERISTICS
- Δ RON = 8 Ω TYP, AT $V_{DD} = 12\text{ V}$
- HIGH LINEARITY – 0.25 % DISTORTION TYP, AT $f = 1\text{ kHz}$, $V_{IN} = 5\text{ V}$, $V_{DD} - V_{SS} = 10\text{ V}$ AND $R_I = 1\ \Omega$
- STANDARD CMOS NOISE IMMUNITY

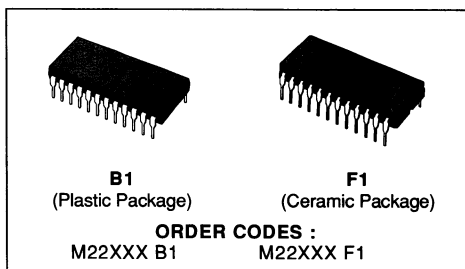
DESCRIPTION

The **M22101** and **M22102** crosspoint switches consist of $4 \times 4 \times 2$ arrays of crosspoints (transmission gates), 4-line to 16-line decoders, and 16 latch circuits. Any one of the sixteen crosspoint pairs can be selected by applying the appropriate four-line address and any number of crosspoint pairs can be ON simultaneously. Corresponding crosspoints in each array are turned on and OFF simultaneously, also.

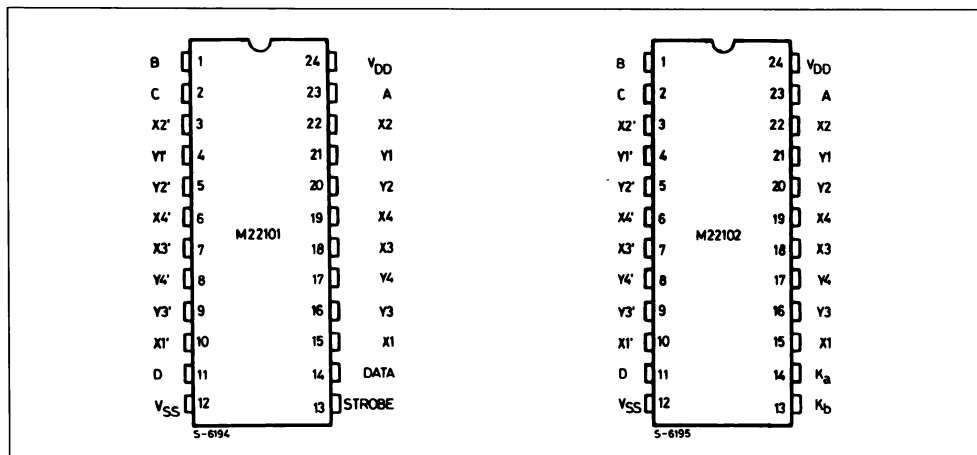
In the **M22101**, the selected crosspoint pair can be turned on or off by applying a logical ONE or ZERO, respectively, to the data input, and applying a ONE to the strobe input. When the device is "power-up", the state of the 16 switches is indeterminate.

Therefore all switches must be turned off by putting the strobe high, data-in-low, and the addressing all switches in succession.

The selected pair of crosspoints in the **M22102** is turned on by applying a logical ONE to the K_a (set) input while a logical ZERO is on the K_b (reset) input, and turned off by applying a logical ONE to the K_b input while a logical ZERO is on the K_a input. In this respect the control latches of the **M22102** are similar to SET/RESET flip-flops. They differ, however, in that the simultaneous application of ONES to the K_a and K_b inputs turns off (resets) all crosspoints. All crosspoints in both devices must be turned off as V_{DD} is applied.



PIN CONNECTIONS



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: Ceramic Type	-0.5 to +20	V
	Plastic Type	-0.5 to +18	V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for Top = Full Package Temperature Range	100	mW
T _{op}	Operating Temperature: Ceramic Type	-55 to +125	°C
	Plastic Type	-40 to +85	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: Ceramic Type	3 to 18	V
	Plastic Type	3 to 15	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: Ceramic Type	-55 to +125	°C
	Plastic Type	-40 to +85	°C

CONTROL TRUTH TABLE FOR M22101

Function	Address				Strobe	Data	Select
	A	B	C	D			
Switch1-on	1	1	1	1	1	1	(X4 Y4) & (X4' Y4')
Switch1-off	1	1	1	1	1	0	(X4 Y4) & (X4' Y4')
No CHange	X	X	X	X	0	X	X X X X

Note: 1 = High, 0 = Low, X = Don't Care

CONTROL TRUTH TABLE FOR M22102

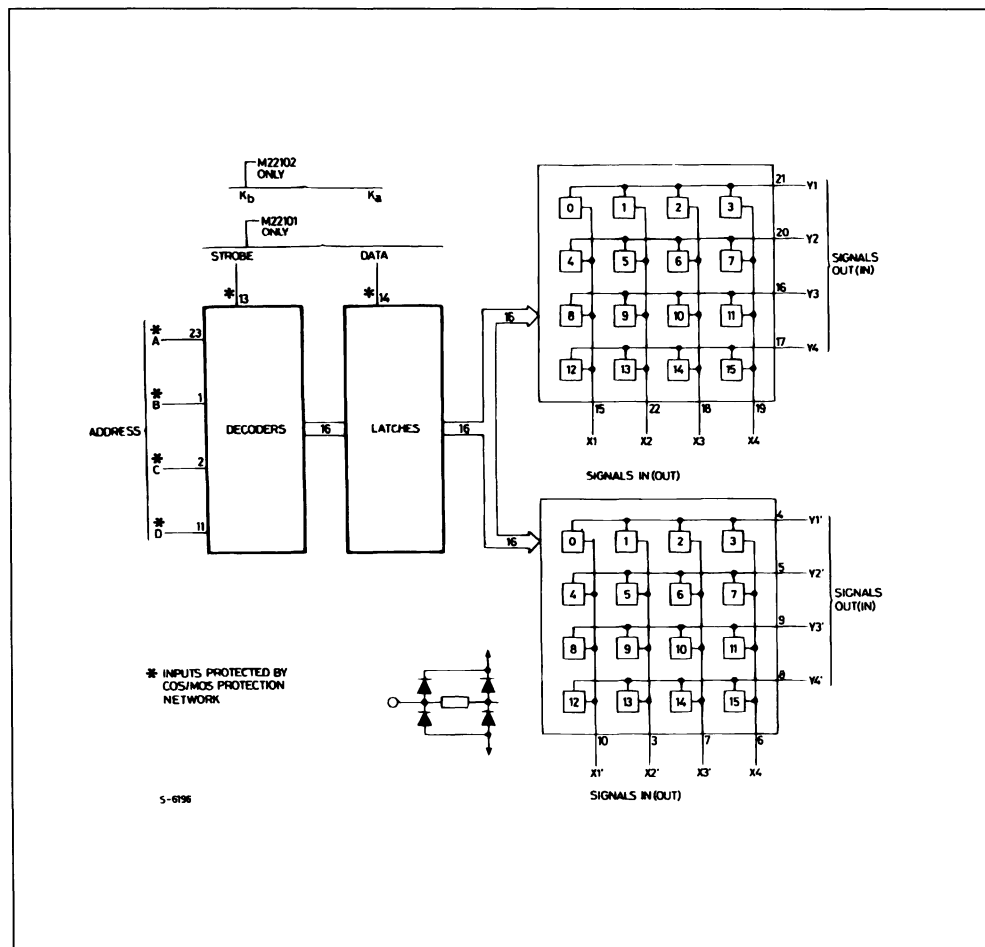
Function	Address				Strobe	Data	Select
	A	B	C	D			
Switch1-on	1	1	1	1	1	0	(X4 Y4) & (X4' Y4')
Switch1-off	1	1	1	1	0	1	(X4 Y4) & (X4' Y4')
All Switch1-off	X	X	X	X	1	1	All
No CHange	X	X	X	X	0	0	X X X X

Note: 1 = High, 0 = Low, X = Don't Care

DECODER TRUTH TABLE

Address				Select		Address				Select	
A	B	C	D			A	B	C	D		
0	0	0	0	X1 Y1	X1' Y1'	0	0	0	1	X1 Y3	X1' Y3'
1	0	0	0	X2 Y1	X2' Y1'	1	0	0	1	X2 Y3	X2' Y3'
0	1	0	0	X3 Y1	X3' Y1'	0	1	0	1	X3 Y3	X3' Y3'
1	1	0	0	X4 Y1	X4' Y1'	1	1	0	1	X4 Y3	X4' Y3'
0	0	1	0	X1 Y2	X1' Y2'	0	0	1	1	X1 Y4	X1' Y4'
1	0	1	0	X2 Y2	X2' Y2'	1	0	1	1	X2 Y4	X2' Y4'
0	1	1	0	X3 Y2	X3' Y2'	0	1	1	1	X3 Y4	X3' Y4'
1	1	1	0	X4 Y2	X4' Y2'	1	1	1	1	X4 Y4	X4' Y4'

FUNCTIONAL AND BLOCK DIAGRAM



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions				Value						Unit	
		V _I (V)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *				
				Min.	Max.	Min.	Typ.	Max.	Min.	Max.			
CROSSPOINT													
I _L	Quiescent Supply Current	F1	Any Switch	5				0.04	5		150	μA	
				10				0.04	10		300		
				15				0.04	20		600		
				20				0.08	100		3000		
		B1		5				0.04	20		150		
				10				0.04	40		300		
R _{ON}	On Resistance	F1	Any Switch	5		450		225	1250		1625	Ω	
				10		135		85	180		230		
				12		100		75	135		175		
				15		70		65	95		125		
		B1		V _{IS} = 0 to V _{DD}	5		1000		225	1250			1440
					10		145		85	180			205
					12		110		75	135			155
					15		75		65	95			110
ΔON	Resistance ΔR _{ON} (Between any two channels)			5				35			Ω		
				10				20					
				12				18					
				15				15					
OFF Channel Leakage Current		F1	All Switch OFF	0/18	18		±0.1	±10 ⁻³	±0.1		±1	μA	
		B1		0/15	15		±0.3	±10 ⁻³	±0.3		±1		
CONTROL													
V _{IL}	Input Low Voltage		OFF Switch I _L < 0.2 μA	5		1.5			1.5		1.5	V	
				10		3			3		3		
				15		4			4		4		
V _{IH}	Input High Voltage		ON Switch see R _{ON} Characteristics	5	3.5		3.5			3.5		V	
				10	7		7			7			
				15	11		11			11			
I _I	Input Current	F1	Any Control Input	0/18	18		±0.1	±10 ⁻⁵	±0.1		±1	μA	
		B1		0/15	15		±0.3	±10 ⁻⁵	±0.3		±1		
C _I	Input Capacitance		Any Input					5	7.5		pF		

* Determined by minimum feasible leakage measurement for automatic testing

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.

* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device

The Noise Margin for both "1" and "0" level is 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

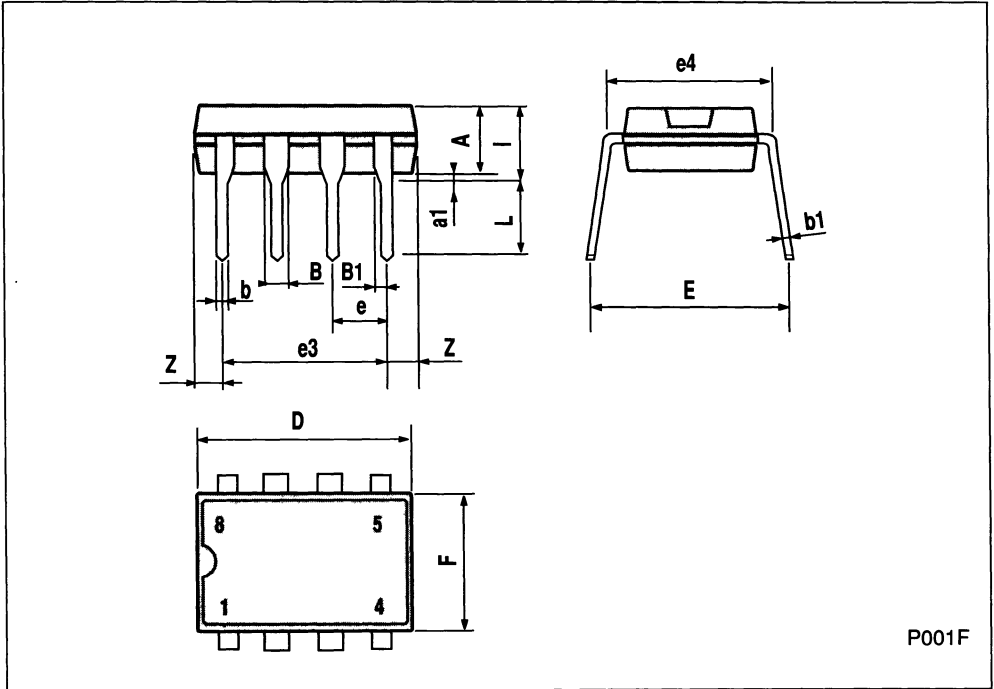
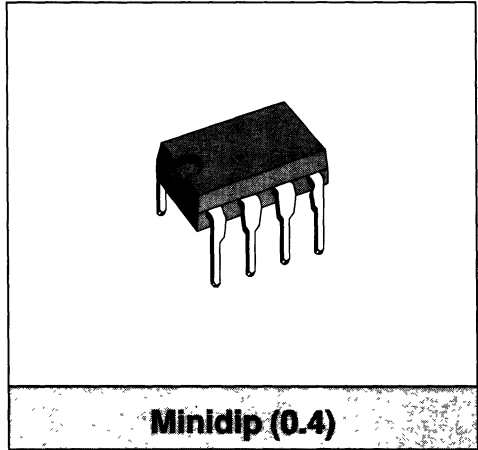
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time Address or Strobe Inputs to Output	$R_L = 10\text{ K}\Omega$ $C_L = 50\text{ pF}$	12		200		ns
t_{PHL} t_{PLH}	Propagation Delay Time Across Crosspoint				20		ns
	Minimum Strobe Pulse Width				80		ns

PACKAGES

DIM.	mm			Inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		3.3			0.130	
a1	0.7			0.028		
B	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.5	0.015		0.020
D			9.8			0.386
E		8.8			0.346	
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	
Z	0.44		1.6	0.017		0.063

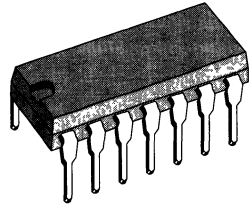


OUTLINE AND MECHANICAL DATA



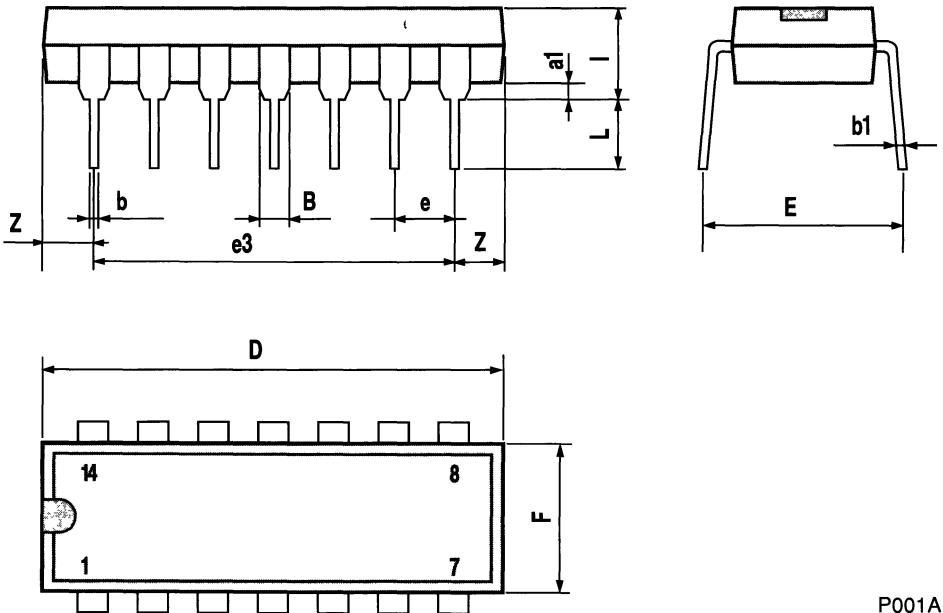
P001F

OUTLINE AND MECHANICAL DATA

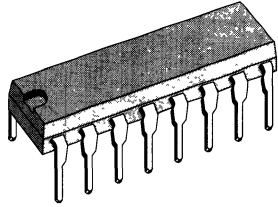


Plastic DIP14

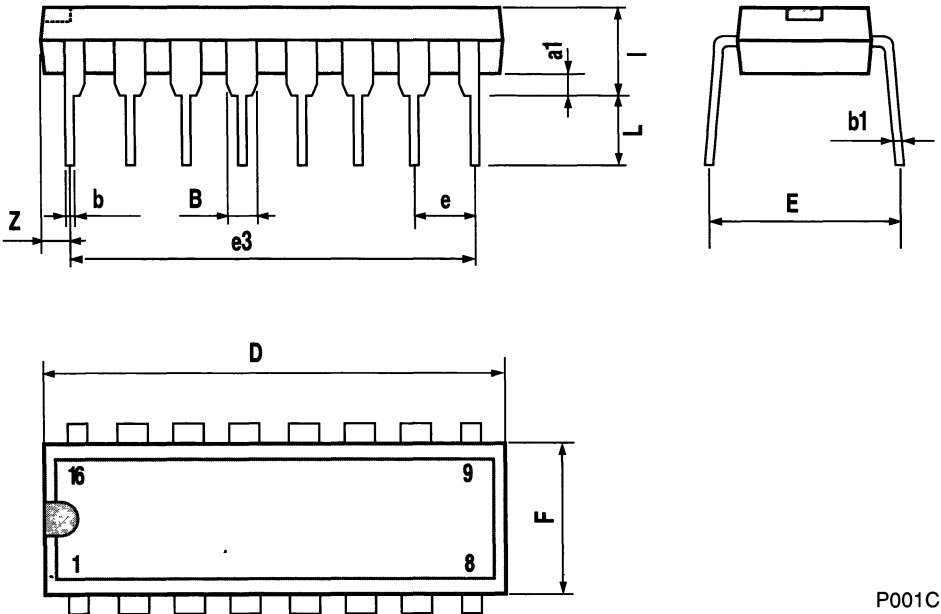
DIM.	mm			Inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

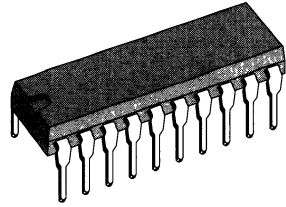
**OUTLINE AND
 MECHANICAL DATA**

Plastic DIP16 (0.25)

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



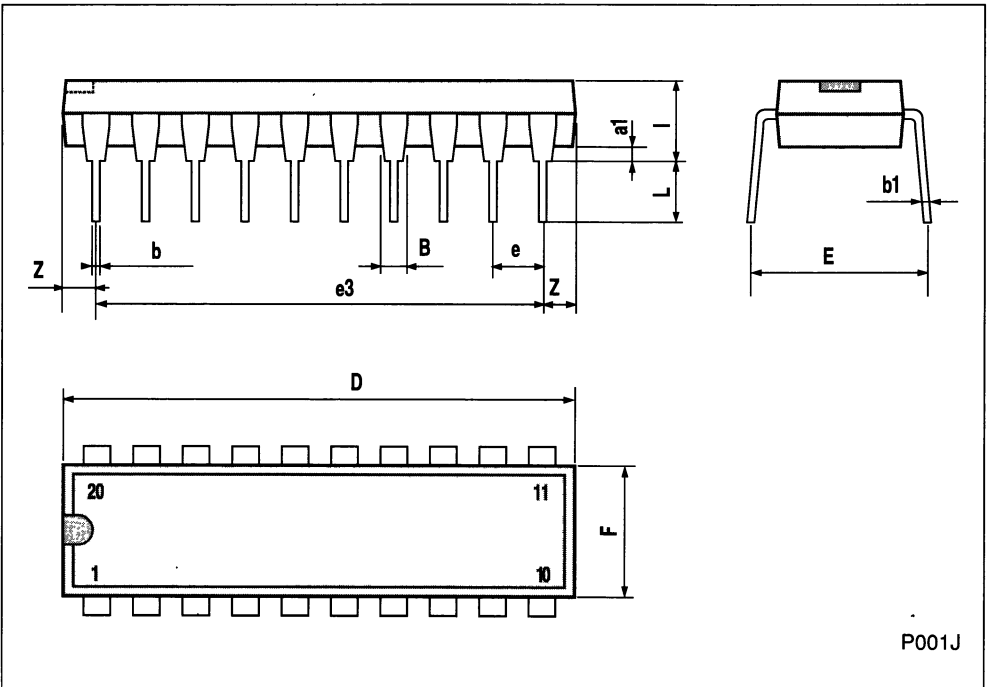
P001C

OUTLINE AND MECHANICAL DATA



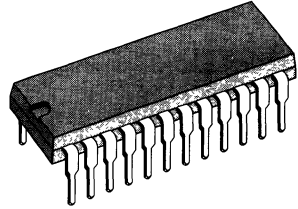
Plastic DIP20 (0.25)

DIM.	mm			Inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



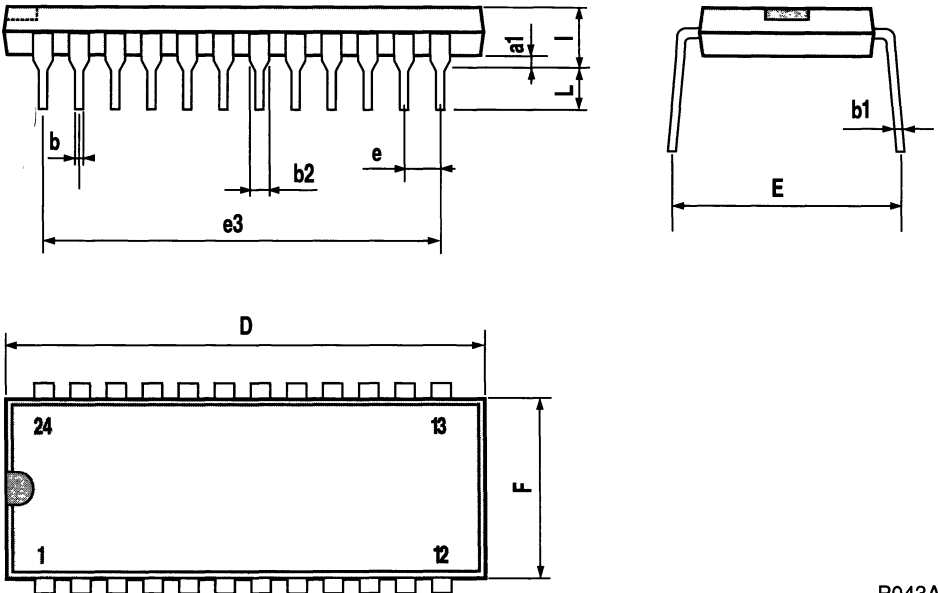
P001J

OUTLINE AND MECHANICAL DATA



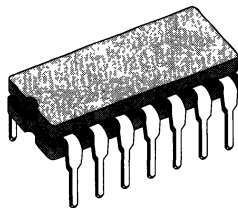
Plastic DIP24 (0.25)

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1		0.63			0.025	
b		0.45			0.018	
b1	0.23		0.31	0.009		0.012
b2		1.27			0.050	
D			32.2			1.268
E	15.2		16.68	0.598		0.657
e		2.54			0.100	
e3		27.94			1.100	
F			14.1			0.555
l		4.445			0.175	
L		3.3			0.130	



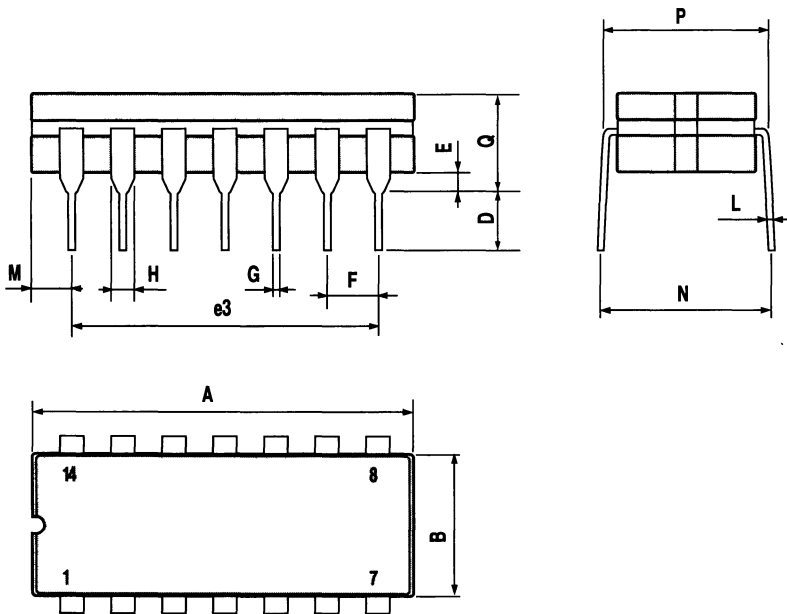
P043A

OUTLINE AND MECHANICAL DATA



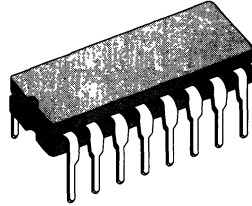
Ceramic DIP14/1

DIM.	mm			Inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



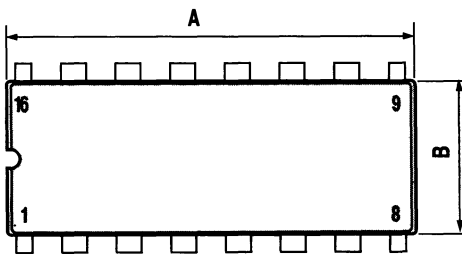
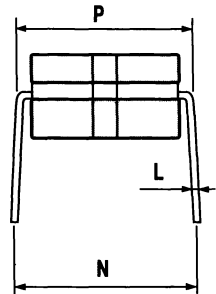
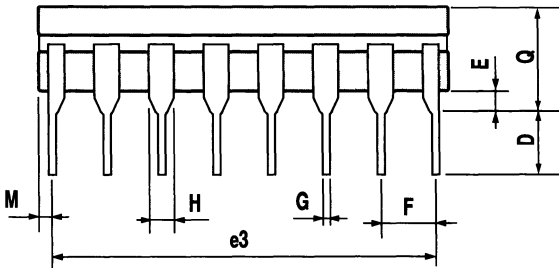
P053C

OUTLINE AND MECHANICAL DATA

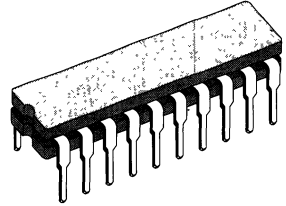


Ceramic DIP16/1

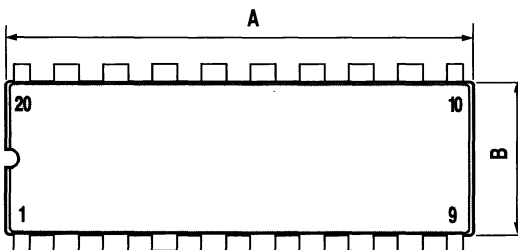
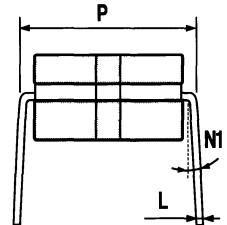
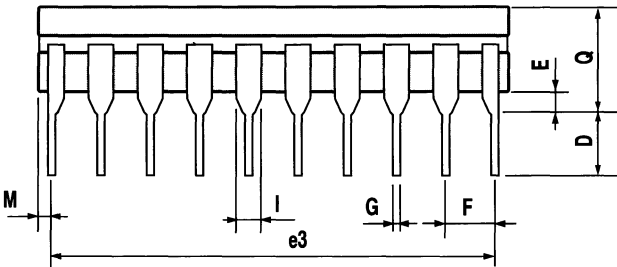
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053D

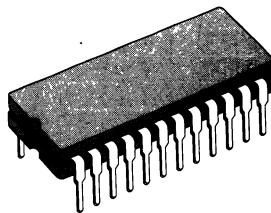
**OUTLINE AND
 MECHANICAL DATA**

Ceramic DIP20

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			25			0.984
B			7.8			0.307
D		3.3			0.130	
E	0.5		1.78	0.020		0.070
e3		22.86			0.900	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.27		1.52	0.050		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N1	4° (min.), 15° (max.)					
P	7.9		8.13	0.311		0.320
Q			5.71			0.225



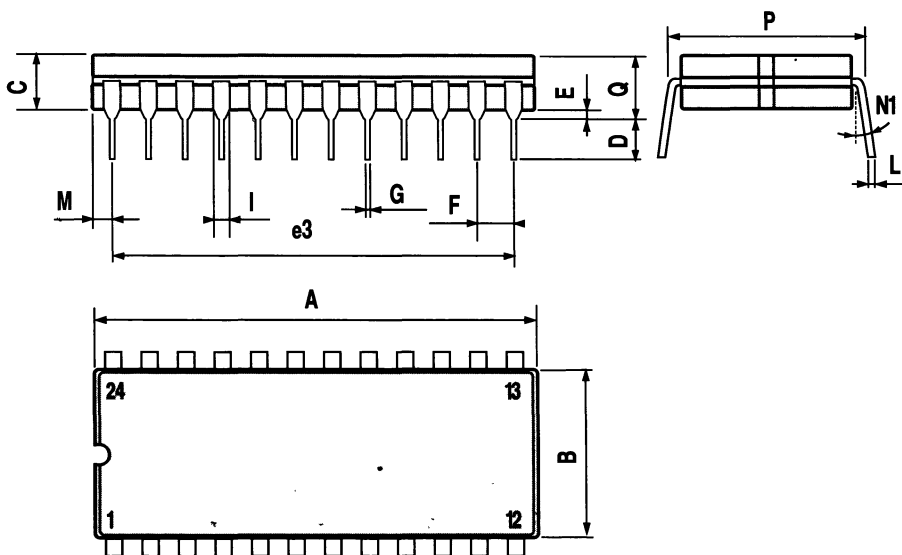
P057H

OUTLINE AND MECHANICAL DATA



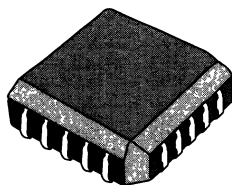
Ceramic DIP24

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			32.3			1.272
B	13.05		13.36	0.514		0.526
C	3.9		5.08	0.154		0.200
D	3			0.118		
E	0.5		1.78	0.020		0.070
e3		27.94			1.100	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.49	0.060		0.098
N1	4° (min.), 15° (max.)					
P	15.4		15.8	0.606		0.622
Q			5.71			0.225



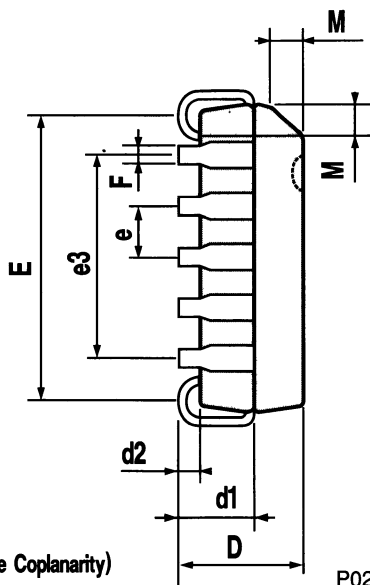
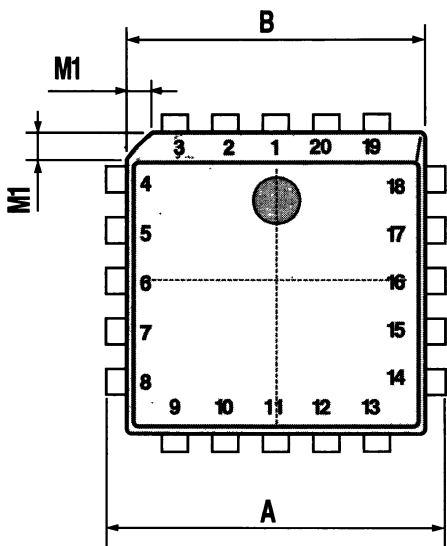
P058C

OUTLINE AND MECHANICAL DATA



PLCC20

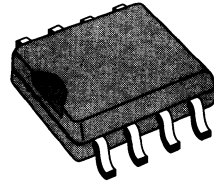
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



 G (Seating Plane Coplanarity)

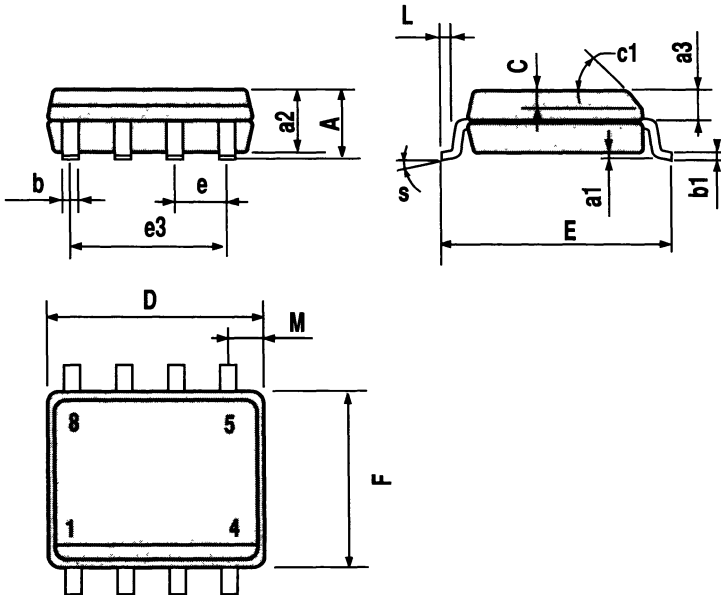
P027A

OUTLINE AND MECHANICAL DATA



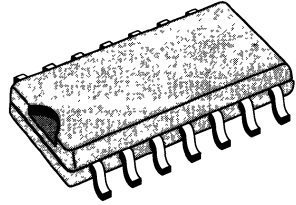
SO8

DIM.	mm			Inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					



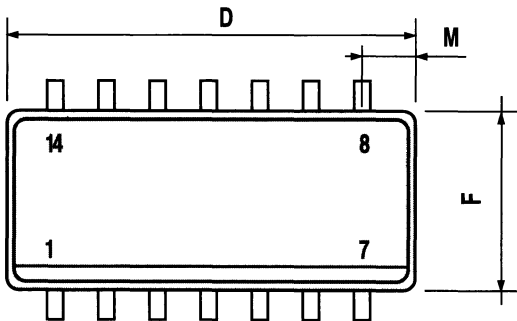
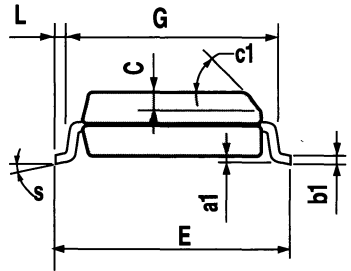
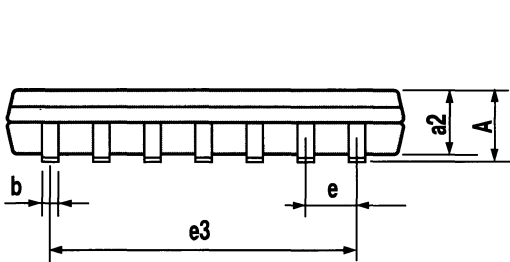
P013M

OUTLINE AND MECHANICAL DATA



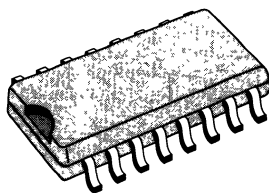
SO14

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.069
a1	0.1		0.2	0.004		0.008
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.020	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.15		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.020		0.050
M			0.68			0.027
S	8° (max.)					



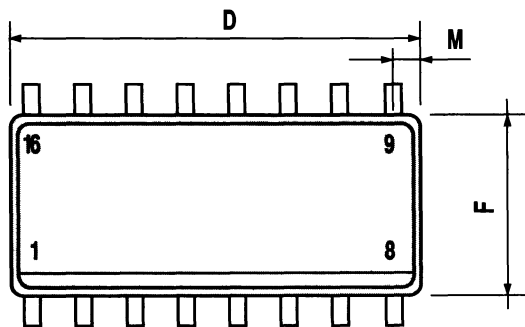
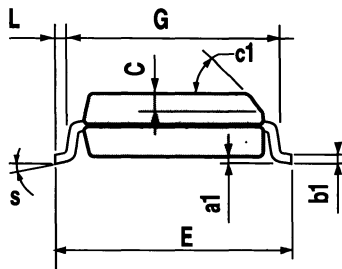
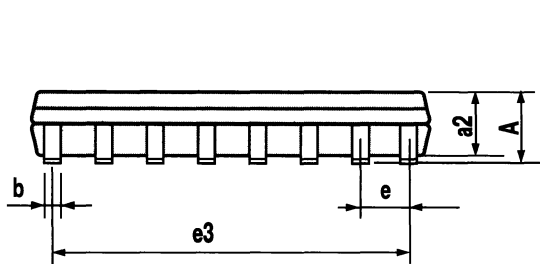
P013G

OUTLINE AND MECHANICAL DATA



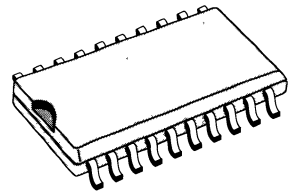
SO16

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.069
a1	0.1		0.2	0.004		0.008
a2			1.6			0.063
b	0.35		0.46	0.014		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.020	
c1	45° (typ.)					
D	9.8		10	0.386		0.394
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.150		0.157
G	4.6		5.3	0.181		0.209
L	0.5		1.27	0.020		0.050
M			0.62			0.024
S	8° (max.)					



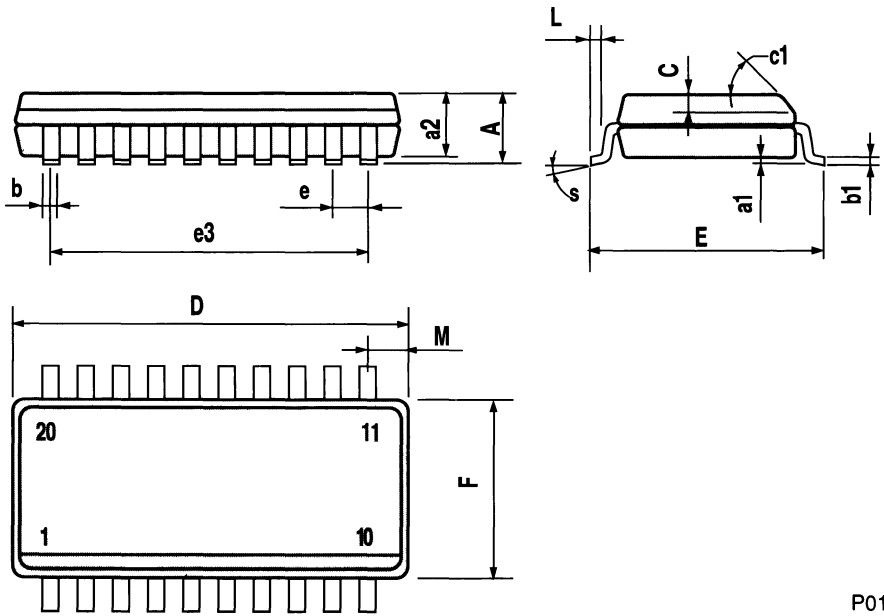
P013H

OUTLINE AND MECHANICAL DATA



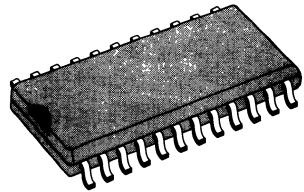
SO20

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.013
C		0.5			0.020	
c1	45° (typ.)					
D	12.6		13.0	0.496		0.510
E	10		10.65	0.394		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.4		7.6	0.291		0.300
L	0.5		1.27	0.020		0.050
M			0.75			0.030
S	8° (max.)					



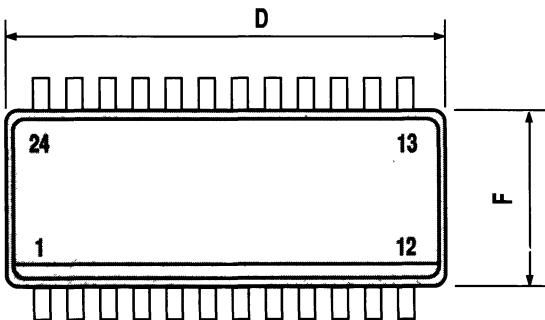
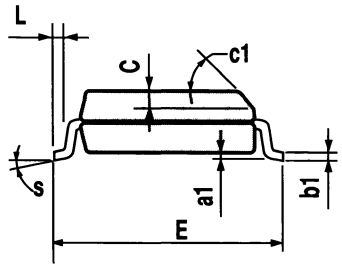
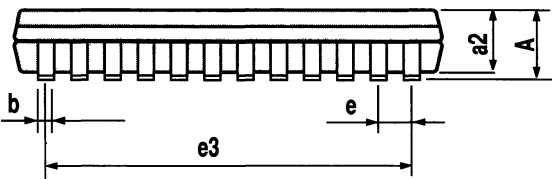
P013L

**OUTLINE AND
MECHANICAL DATA**



SO24

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.013
C		0.5			0.020	
c1	45° (typ.)					
D	15.2		15.6	0.598		0.614
E	10		10.65	0.394		0.419
e		1.27			0.050	
e3		13.97			0.550	
F	7.4		7.6	0.291		0.300
L	0.5		1.27	0.020		0.050
M			0.75			0.030
S	8° (max.)					



NOTES

EUROPE

DENMARK

2730 HERLEV

Herlev Torv, 4
Tel (45-42) 94.85 33
Telex 35411
Telefax (45-42) 948694

FINLAND

LOHJA SF-08150

Karjalankatu, 2
Tel (358-12) 155 11
Telefax (358-12) 155 66

FRANCE

94253 GENTILLY Cedex

7 - avenue Gallieni - BP 93
Tel (33-1) 47 40 75 75
Telex 632570 STMHQ
Telefax (33-1) 47 40 79 10

67000 STRASBOURG

20, Place des Halles
Tel (33) 88 75 50 66
Telex 870001F
Telefax (33) 88 22 29 32

GERMANY

6000 FRANKFURT

Gutleutstrasse 322
Tel (49-69) 237492-3
Telex 176997 689
Telefax (49-69) 231957
Teletex. 6997689=STVBP

8011 GRASBRUNN

Bretonischer Ring 4
Neukeferloh Technopark
Tel (49-89) 46006-0
Telex 528211
Telefax (49-89) 4605454
Teletex 897107=STDISTR

3000 HANNOVER 51

Rotenburger Strasse 28A
Tel (49-511) 615960
Telex 175118418
Teletex 5118418 CSFBEH
Telefax (49-511) 6151243

5202 HENNEF

Reuther Strasse 1A-C
Tel (49-2242) 6088
(49-2242) 4019/4010
Telefax (49-2242) 84181

8500 NÜRNBERG 20

Erlenstegenstrasse, 72
Tel (49-911) 59893-0
Telex 626243
Telefax (49-911) 5980701

7000 STUTTGART 31

Mittlerer Pfad 2-4
Tel (49-711) 13968-0
Telex 721718
Telefax (49-711) 8661427

ITALY

20090 ASSAGO (MI)

V.le Milanofiori - Strada 4 - Palazzo A/4/A
Tel (39-2) 89213 1 (10 linee)
Telex 330131 - 330141 SGSAGR
Telefax (39-2) 8250449

40033 CASALECCHIO DI RENO (BO)

Via R. Fucini, 12
Tel (39-51) 591914
Telex 512442
Telefax (39-51) 591305

00161 ROMA

Via A. Torlonia, 15
Tel (39-6) 8443341
Telex 620653 SGSATE I
Telefax (39-6) 8444474

NETHERLANDS

5652 AR EINDHOVEN

Meerenakkerweg 1
Tel (31-40) 550015
Telex 51186
Telefax (31-40) 528835

SPAIN

08021 BARCELONA

Calle Platon, 6 4th Floor, 5th Door
Tel (34-3) 4143300-4143361
Telefax (34-3) 2021461

28027 MADRID

Calle Alpacete, 5
Tel (34-1) 4051615
Telex 46033 TCCEE
Telefax (34-1) 4031134

SWEDEN

S-16421 KISTA

Borgarfjordsgatan, 13 - Box 1094
Tel (46-8) 7939220
Telex 12078 THSWS
Telefax (46-8) 7504950

SWITZERLAND

1218 GRAND-SACONNEX (GENEVA)

Chemin Francois-Lehmann, 18/A
Tel (41-22) 7986462
Telex 415493 STM CH
Telefax (41-22) 7984869

UNITED KINGDOM and EIRE

MARLOW, BUCKS

Planar House, Parkway
Globe Park
Tel (44-628) 890800
Telex 847458
Telefax (44-628) 890391

AMERICAS**BRAZIL**

05413 SÃO PAULO
R Henrique Schaumann 286-CJ33
Tel (55-11) 883-5456
Telex (3911)11-37988 'UMBR BR'
Telefax (55-11) 282-2367

U.S.A.

**NORTH & SOUTH AMERICAN
MARKETING HEADQUARTERS**
1000 East Bell Road
Phoenix, AZ 85022
(1-602) 867-6100

SALES COVERAGE BY STATE**ALABAMA**

Huntsville - (205) 533-5995

ARIZONA

Phoenix - (602) 867-6217

CALIFORNIA

Santa Ana - (714) 957-6018
San Jose - (408) 452-8585

COLORADO

Boulder (303) 449-9000

ILLINOIS

Schaumburg - (708) 517-1890

INDIANA

Kokomo - (317) 459-4700

MASSACHUSETTS

Lincoln - (617) 259-0300

MICHIGAN

Livonia - (313) 462-4030

NEW JERSEY

Voorhees - (609) 772-6222

NEW YORK

Poughkeepsie - (914) 454-8813

NORTH CAROLINA

Raleigh - (919) 787-6555

TEXAS

Carrollton - (214) 466-8844

**FOR RF AND MICROWAVE
POWER TRANSISTORS CON-
TACT**

**THE FOLLOWING REGIONAL
OFFICE IN THE U.S.A.**

PENNSYLVANIA

Montgomeryville - (215) 361-6400

ASIA / PACIFIC**AUSTRALIA**

NSW 2027 EDGECLIFF
Suite 211, Edgecliff centre
203-233, New South Head Road
Tel (61-2) 327 39 22
Telex 071 126911 TCAUS
Telefax (61-2) 327 61 76

HONG KONG**WANCHAI**

22nd Floor - Hopewell centre
183 Queen's Road East
Tel (852-5) 8615788
Telex 60955 ESGIES HX
Telefax (852-5) 8656589

INDIA**NEW DELHI 110001**

Liason Office
62, Upper Ground Floor
World Trade Centre
Barakhamba Lane
Tel (91-11) 3715191
Telex 031-66816 STMI IN
Telefax (91-11) 3715192

MALAYSIA**PULAU PINANG 10400**

4th Floor - Suite 4-03
Bangunan FOP-123D Jalan Anson
Tel (04) 379735
Telefax (04) 379816

KOREA**SEOUL 121**

8th floor Shinwon Building
823-14, Yuksam-Dong
Kang-Nam-Gu
Tel (82-2) 553-0399
Telex SGSKOR K29998
Telefax (82-2) 552-1051

SINGAPORE**SINGAPORE 2056**

28 Ang Mo Kio - Industrial Park 2
Tel (65) 4821411
Telex RS 55201 ESGIES
Telefax (65) 4820240

TAIWAN**TAIPEI**

12th Floor
325 Section 1, Tun Hua South Road
Tel (886-2) 755-4111
Telex 10310 ESGIE TW
Telefax (886-2) 755-4008

JAPAN**TOKYO 108**

Nisseki - Takanawa Bld 4F
2-18-10 Takanawa
Minato-Ku
Tel (81-3) 3280-4121
Telefax (81-3) 3280-4131

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1991 SGS-THOMSON Microelectronics – Printed in Italy – All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - United Kingdom - U.S.A.



Kcs 30300

ORDER CODE: DBCMOSBST1